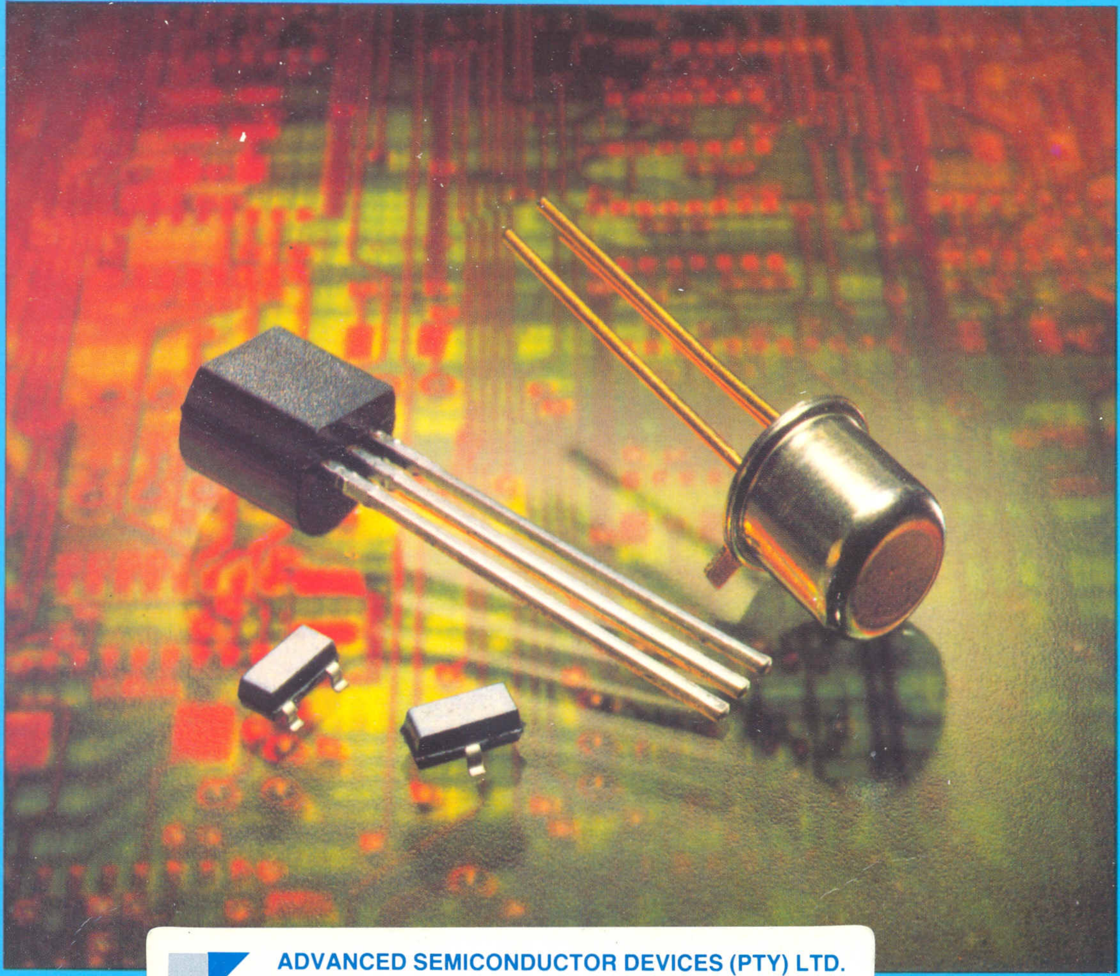
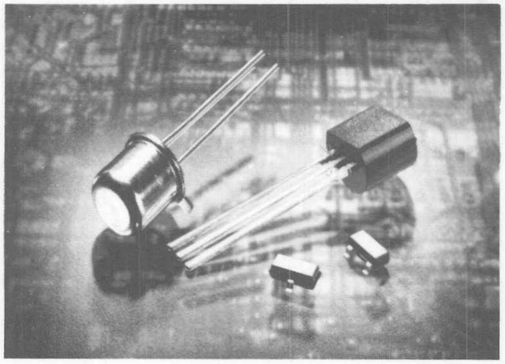
DLE126R1/D

MOTOROLA Semiconductors



SMALL-SIGNAL SEMICONDUCTORS



MOTOROLA

SMALL-SIGNAL SEMICONDUCTORS

This publication presents technical information for the several product families that comprise the Motorola small-signal semiconductor line. The families includes bipolar, field-effect transistors, and diodes. These are available in a variety of packages; metal can, plastic, and surface mount. Complete device specifications and typical performance curves are given on individual data sheets, which are grouped by the various families.

A quick comparison of performance characteristics is presented in the easy-to-use selector guides in the first section. The tables will assist in the selection of the proper transistor for a specific application.

Separate sections are included to describe package outline drawings, and to clarify the high reliability processing and testing procedure.

The information in this book has been carefully checked and is believed to be accurate; however, no responsibility is assumed for inaccuracies. Furthermore, this information does not convey to the purchaser of semiconductor devices any license under the patent rights to the manufacturer.

Motorola reserves the right to make changes without further notice to any products herein to improve reliability, function or design. Motorola does not assume any liability arising out of the application or use of any product or circuit described herein; neither does it convey any license under its patent rights nor the rights of others. Motorola and Ⓜ are registered trademarks of Motorola, Inc.

ISBN 1 870760 08 5

First Edition 1984 – DLE126/D
Second Edition 1988 – DLE126R1/D
Printed in Great Britain by Oxford University Press, 10,000 4/88.

ALPHANUMERIC INDEX

Devices with no page number shown are available from Motorola although not represented in this book. Please contact your nearest Motorola representative for further information.

Devices with no page number shown are available from Motorola although not represented in this book. Please contact your nearest Motorola representative for further information.

Devices with no page number shown are available from Motorola although not represented in this book. Please contact your nearest Motorola representative for further information.

Devices with no page number shown are available from Motorola although not represented in this book. Please contact your nearest Motorola representative for further information

ALPHANUMERIC INDEX (continued)

Devices with no page number shown are available from Motorola although not represented in this book. Please contact your nearest Motorola representative for further information.

Devices with no page number shown are available from Motorola although not represented in this book. Please contact your nearest Motorola representative for further information.

ALPHANUMERIC INDEX (continued)

Motorola Part #	Data Sheet Page #
MD7021,F	5-103
MD8001	5-105
MD8002	5-105
MD8003	5-105
MFE120	6-132
MFE121	6-132
MFE122	6-132
MFE130	6-136
MFE131	6-136
MFE132	6-136
MFE140	6-139
MFE823	6-144
MFE825	6-145
MFE910	6-146
MFE930	6-148
MFE960	6-148
MFE990	6-148
MFE2004	6-151
MFE2005	6-151
MFE2006	6-151
MFE2010	6-153
MFE2011	6-153
MFE2012	6-153
MFE9200	6-155
MFQ930C	6-158
MFQ960C	6-158
MFQ990C	6-158
MHQ918	5-106
MHQ2222	5-107
MHQ2369	5-109
MHQ2906	5-110
MHQ3467	5-112
MHQ3546	5-113
MHQ3798	5-114
MHQ4002A	5-115
MHQ4013	5-116
MHQ4014	5-116
MHQ6001	5-118
MHQ6002	5-118
MM1748A	4-264
MM2005	4-265
MM3001	4-266
MM3002	4-266
MM3003	4-266
MM3005	4-267
MM3006	4-267
MM3007	4-267
MM3009	4-268
MM3903	4-269
MM3904	4-269
MM3905	4-271
MM3906	4-271
MM4000	4-273
MM4001	4-273
MM4002	4-273
MM4003	4-273

Motorola Part #	Data Sheet Page #
MM4005	4-274
MM4036	4-275
MM4037	4-275
MM4257	4-277
MM4258	4-277
MM5005	4-280
MM5006	4-280
MM5007	4-280
MM5262	4-281
MM5415	4-282
MM5416	4-282
MM6427	4-283
MMAD130	3-47
MMAD1103	3-47
MMAD1104	3-47
MMAD1105	3-47
MMAD1106	3-47
MMAD1107	3-47
MMAD1108	3-49
MMAD1109	3-47
MMBA811C5,C6,C7,C8	3-50
MMBA812M3,M4,M5,M6,M7	3-51
MMBC1009F1,F3	3-52
MMBC1321Q3,Q4,Q5	3-53
MMBC1622D6,D7	3-54
MMBC1623L3,L4,L5,L6,L7	3-55
MMBC1653N2,N3,N4	3-56
MMBC1654N5,N6,N7	3-57
MMBD101	3-58
MMBD201	3-59
MMBD301	3-59
MMBD352	3-60
MMBD353	3-60
MMBD501	3-59
MMBD701	3-59
MMBD914X	3-61
MMBD2835X	3-62
MMBD2836X	3-62
MMBD2837X	3-63
MMBD2838X	3-63
MMBD6050X	3-64
MMBD6100	3-65
MMBD7000	3-66
MMBF170	3-67
MMBF4391	3-68
MMBF4392	3-68
MMBF4393	3-68
MMBF4416	3-69
MMBF4860	3-70
MMBF5457	3-72
MMBF5459	3-73
MMBF5460	3-74
MMBF5484	3-75
MMBF5486	3-76
MMBFJ310	3-77

Devices with no page number shown are available from Motorola although not represented in this book Please contact your nearest Motorola representative for further information

ALPHANUMERIC INDEX (continued)

Devices with no page number shown are available from Motorola although not represented in this book. Please contact your nearest Motorola representative for further information.

Devices with no page number shown are available from Motorola although not represented in this book Please contact your nearest Motorola representative for further information

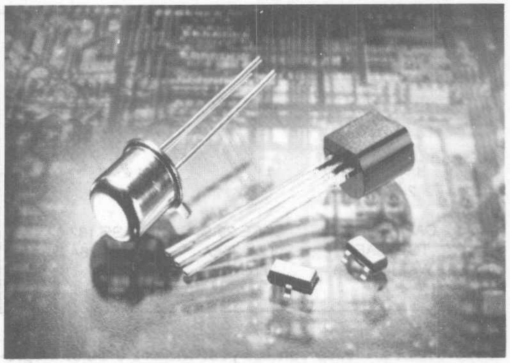
ALPHANUMERIC INDEX (continued)

Devices with no page number shown are available from Motorola although not represented in this book. Please contact your nearest Motorola representative for further information.

ALPHANUMERIC INDEX (continued)

Motorola Part #	Data Sheet Page #

Devices with no page number shown are available from Motorola although not represented in this book Please contact your nearest Motorola representative for further information



The following selector guides highlight semiconductors that are the most popular and have a history of high usage for the most applications.

These selector guides cover a wide range of small signal plastic and metal can semiconductors.

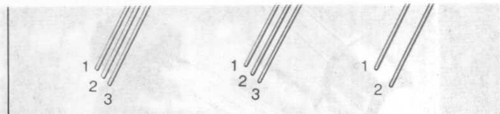
A large selection of encapsulated plastic transistors, FETs and diodes are available for surface mount and insertion assembly technology. Plastic packages include TO-226AA, TO-226AE 1 Watt and SOT-23. Plastic multiples are available in 14-pin and 16-pin dual-in-line packages for insertion applications: SO-8, SO-14 and SO-16 for surface mount applications.

Metal can and ceramic packages are available for applications requiring higher power dissipation or having hermetic requirements. TO-18, TO-205AD, TO-46, TO-52 and TO-72 packages contain discrete devices. There is a variety of ceramic dip and flatpacks available for multiple transistors, FETs and diodes.

Devices which are JAN, JANTX, JTXV or CECC qualified are noted in the individual selector guides or in the Hi-Rel and Military Section of this selector guide.

Table of Contents

Plastic-Encapsulated



CASE 29-03 TO-226AE (1 WATT TO-92) | CASE 29-04 TO-226AA (TO-92) | CASE 182-02 TO-226AC

Motorola's small-signal TO-226 plastic transistors encompass hundreds of devices with a wide variety of characteristics for general purpose, amplifier and switching applications. The popular high-volume package combines proven reliability, performance, economy and convenience to provide the perfect solution for industrial and consumer design problems. All devices are laser marked for ease of identification and shipped in antistatic containers, as part of Motorola's ongoing practice of maintaining the highest standards of quality and reliability.

In addition to the standard devices listed in the following tables, Motorola also offers special electrical selections of these devices. Please contact your Motorola Sales Representative regarding any special requirements you may have.

In each of the following tables, the ajor specifications of the transistors or diodes are given for easy comparison.

All transistors are available in the radial or axial tape and reel formats. Lead forming to fit TO-5 or TO-18 sockets is also available.

TABLE 1. General-Purpose Amplifier Transistors

The general-purpose transistors are designed for small-signal amplification from dc to low radio frequencies. They are also useful as oscillators and general purpose switches.

NPN	PNP	Pin Out	$V_{(BR)CEO}$ Volts Min	f_T @ I_C MHZ Min	mA	I_C mA Max	h_{FE} @ I_C Min	Max	mA	NF Max dB
TO-226AA										
MPS8099	MPS8599	EBC	80	150	10	200	100	300	1	—
MPSA06	MPSA56	EBC	80	100	10	50	50	—	100	—
BC546	BC556	CBE	65	150	10	100	120	450	2	10
BC546A	BC556A	CBE	65	150	10	100	120	220	2	10
BC546B	BC556B	CBE	65	150	10	100	180	450	2	10
MPS8098	MPS8598	EBC	60	150	10	200	100	300	1	—
MPSA05	MPSA55	EBC	60	100	10	500	50	—	100	—
MPS651	MPS751	EBC	60	75	50	2000	40	—	2000	—
BC182	BC212	CBE	50	200	10	100	120	460	2	10
BC237	BC307	CBE	45	150	10	100	120	460	2	10
BC239	BC309	CBE	45	150	10	100	180	800	2	10
BC547	BC557	CBE	45	150	10	100	120	450	2	10
BC547A	BC557A	CBE	45	150	10	100	120	220	2	10
BC547B	BC557B	CBE	45	150	10	100	180	450	2	10
BC547C	BC557C	CBE	45	150	10	100	380	800	2	10
BC317	BC320	CBE	45	250	10	150	110	450	2	10
2N3904	2N3906	EBC	40	300	10	200	100	300	10	5
2N4401	2N4403	EBC	40	250	20	600	100	300	150	—
2N3903	2N3905	EBC	40	250	10	200	50	150	100	6
2N4400	2N4402	EBC	40	200	20	600	50	150	150	—
MPSA20	MPSA70	EBC	40	125	5	100	40	400	5	—
MPS650	MPS750	EBC	40	75	50	2000	40	—	2000	—
MPS6531	MPS6534	EBC	40	390*	50	600	10	120	100	—
MPS2222	MPS2907	EBC	30	250	20	600	100	300	150	—
2N4123	2N4125	EBC	30	250	10	200	50	150	2	—
MPS3704	MPS3702	EBC	30	100	50	600	100	300	50	—
MPS6513	MPS6517	EBC	30	330*	10	100	90	180	2	—
BC548	BC558	CBE	30	300*	10	100	120	300	2	10
BC548A	BC558A	CBE	30	300*	10	100	120	220	2	10
BC548B	BC558B	CBE	30	300*	10	100	180	450	2	10
BC548C	BC558C	CBE	30	300	10	100	380	800	2	10
2N4124	2N4126	EBC	25	300	10	200	120	360	2	—
MPS6514	MPS6518	EBC	25	480*	10	100	150	300	2	—
MPS6515	MPS6519	EBC	25	480	10	100	250	500	2	—
MPS5172		EBC	25	120*	5	100	100	500	10	—
MPS6560	MPS6562	EBC	25	60	10	500	50	200	600	—
MPS6601	MPS6551	EBC	25	100	50	1000	30	150	1000	—
BC238	BC308	CBE	25	150	10	100	120	800	2	10

TABLE 2. Low-Noise and Good h_{FE} Linearity

These devices are designed to use on applications where good h_{FE} linearity and low noise characteristics are required: Instrumentation, Hi-Fi Preamplifier.

NPN	PNP	Pin Out	$V_{(BR)CEO}$ Volts	h_{FE} Min	h_{FE} Max	I_C mA	V_T mV Typ	NF dB Max	f_T Typ MHz
TO-226AA									
—	MPS4249	EBC	60	100	—	10	—	3	100
—	2N5087	EBC	60	250	—	10	—	2	40
—	MPS425A	EBC	60	250	—	10	—	2	250
—	2N5086	EBC	50	150	—	10	—	3	40
BC239	BC309	CBE	45	120	800	2	9.5	2	240
BC414	BC416	CBE	45	180	800	2	8	2.5	250
BC550	BC560	CBE	45	180	800	2	8	2.5	250
BC550B	BC560B	CBE	45	180	460	2	8	2.5	250
BC550C	BC560C	CBE	45	380	800	2	8	2.5	250
BC651	—	EBC	45	380	1400	2	—	—	300
MPSA18	—	EBC	45	500	—	2	7	—	160
—	MPS4250	EBC	40	250	—	10	—	2	250
BC413	BC415	CBE	30	180	800	2	8	2.5	250
BC549	BC559	CBE	30	180	800	2	8	2.5	250
BC549B	BC559B	CBE	30	180	800	2	8	2.5	250
BC459C	BC459C	CBE	30	380	800	2	8	2.5	250
BC650	—	EBC	30	380	1400	2	—	—	300
2N4123	2N4125	EBC	30	50	150	2	—	6	300
2N5088	—	EBC	30	350	—	2	—	3	150
2N4124	2N4126	EBC	25	120	360	2	—	5	350
2N5089	—	EBC	25	450	—	2	—	2	150
—	MPS6523	EBC	25	300	—	2	—	3	340*

1 V_T: Total Input Noise Voltage (see BC413/BC414 and BC415/BC416 Data Sheets) at $R_S = 2\ k\Omega$, $I_C = 200\ \mu A$, $V_{CE} = 5$ Volts.
2 N_F: Noise Figure at $R_S = 2$ k, $I_C = 200\ \mu A$, $V_{CE} = 5$ Volts. f = 30 Hz to 15 kHz.
3 At $V_{CE} = 1$ V.
* "S" version.
(§) @ 1 kHz.

TABLE 3. Darlington Transistors

Darlington amplifiers are cascade transistors used in applications requiring very high gain and input impedance. These devices have monolithic construction.

NPN	PNP	Pin Out	$V_{(BR)CEO}$ Volts	I_C Max	h_{FE} Min	h_{FE} Max	I_C mA	$V_{CE(sat)}$ Volts Max	$V_{CE(sat)}$ I_C mA	I_B mA	f_T Min	I_C
TO-226AA												
MPSA29	—	EBC	100	500	10K	—	100	1.4	100	0.1	125	10
BC372	—	EBC	100	1000	25K	160K	100	1	250	0.25	100	100
MPSA28	—	EBC	80	500	10K	—	100	1.4	100	0.1	125	10
BC373	—	EBC	80	1000	25K	160K	100	1	250	0.25	100	100
MPSA27	MPSA77	EBC	60	500	10K	—	100	1.5	100	0.1	125	10
BC618	—	CBE	55	1000	10K	50K	200	1.1	200	0.2	150	500
MPSA26	MPSA76	EBC	50	500	10K	—	100	1.5	100	0.1	125	10
MPSA25	MPSA75	EBC	40	500	10K	—	100	1.5	100	0.1	125	10
BC617	—	CBE	40	1000	20K	70K	200	1.1	200	0.2	150	500
2N6427	—	EBC	40	500	20K	200K	100	1.5	500	0.5	125	10
2N6426	—	EBC	40	500	30K	300K	100	1.5	500	0.5	125	10
MPSA14	MPSA64	EBC	30	500	20K	—	100	1.5	100	0.1	125	10
MPSA13	MPSA63	EBC	30	500	10K	—	100	1.5	100	0.1	125	10
BC517	—	CBE	30	400	30K	—	20	1	100	0.1	125	10
—	MPSD54	EBC	25	300	1K	—	100	1	100	0.1	100	10
MPSA12	MPSA62	EBC	20	500	20K	—	10	1	10	0.01	125	10
TO-226AE (1 WATT)												
MPSW6725	—	EBC	50	1000	25K	—	200	1.5	1000	2	100	200
MPSW6724	—	EBC	40	1000	25K	—	200	1.5	1000	2	100	200
MPSW45	—	EBC	40	1000	25K	—	200	1.5	1000	2	100	200
MPSW14	MPSW64	EBC	30	1000	20K	—	100	1.5	100	0.1	125	10
MPSW13	MPSW63	EBC	30	1000	10K	—	100	1.5	100	0.1	125	10

TABLE 4. High-Current Amplifier Transistors

Useful in Low Power Audio Output Stages and Medium Current Switches.

NPN	PNP	Pin Out	$V_{(BR)CEO}$ Volts	P_D mW 25°C Amb	I_C (mA) Cont	h_{FE} Min	h_{FE} Max	@ I_C (mA)	V_{CE} (Volts)	f_T Typical (MHz)
TO-226AA										
BC337	BC327	CBE	45	625	800	100	600	100	1	210
BC338	BC328	CBE	25	625	800	100	600	100	1	210
BC445	BC446	CBE	60	625	300	70	—	10	5	250/200[1]
BC447	BC448	CBE	80	625	300	70	—	10	5	250/200[1]
BC449	BC450	CBE	100	625	300	70	—	10	5	250/200[1]
BC485	BC486	CBE	45	625	1000	60	400	100	2	200/150[1]
BC487	BC488	CBE	60	625	1000	60	400	100	2	200/150[1]
BC489	BC490	CBE	80	625	1000	60	400	100	2	200/150[1]
MPSA05	MPSA55	EBC	60	625	500	50	—	100	1	150/175[1]
MPSA06	MPSA56	EBC	80	625	500	50	—	100	1	150/175[1]
MPS8099	MPS8599	EBC	80	625	500	75	—	100	5	200[1]
2N4409	—	EBC	50	625	250	60	400	10	1	200
2N4410	—	EBC	80	625	250	60	400	10	1	200
MPS650	MPS750	EBC	40	625	2000	75	—	1000	2	100
						40	—	2000	2	

[1]Relevant to PNP.

TABLE 5. High-Voltage Amplifier Transistors

These high-voltage transistors are designed for driving neon bulbs and Nixie* indicator tubes, for direct line operation, and for other applications requiring high-voltage capability at relatively low collector current. These devices are listed in order of decreasing breakdown voltage ($V_{(BR)CEO}$).

Device Type	Pin Out	$V_{(BR)CEO}$ Volts Min	I_C Max mA	h_{FE} Min	@ I_C mA	V_F Volts Max	$V_{CE(sat)}$ @ I_C mA	I_B mA	f_T MHz Min	@ I_C mA
NPN — TO-226AA										
BF844	EBC	400	0.5	40	30	0.5	10	1	50	10
MPSA44	EBC	400	0.3	40	100	0.75	50	5	20	10
BF845	EBC	350	0.5	40	30	0.5	10	1	50	10
MPSA45	EBC	350	0.3	50	100	0.75	50	5	20	10
2N6517	EBC	350	0..5	30	30	0.2	10	1	40	10
BF393	EBC	300	0.5	40	10	0.2	20	2	50	10
MPSA42	EBC	300	0.5	40	30	0.5	20	2	50	10
2N6517	EBC	300	0.5	45	30	0.3	10	1	40	10
BF392	EBC	250	0.5	40	10	0.2	20	2	50	10
2N6515	EBC	250	0.5	50	30	0.3	10	1	40	10
BF391	EBC	200	0.5	40	10	0.2	20	2	50	10
MPSA43	EBC	200	0.5	40	10	0.4	20	2	50	10
2N5551	EBC	160	0.6	80	10	0.15	10	1	100	10
2N5550	EBC	140	0.6	60	10	0.15	10	1	100	10
MPSL01	EBC	100	0.15	20	30	0.2	10	1	40	10
NPN — TO-226AE (1 WATT)										
BDC05	ECB	300	0.5	40	25	2	20	2	60	10
MPS6735	EBC	300	0.3	40	10	2	20	2	50	10
MPSW10	EBC	300	0.3	40	30	0.75	30	3	45	10
MPSW42	EBC	300	0.3	40	30	0.5	20	2	50	10
BDC07	ECB	250	0.5	200	50	2	20	2	60	10
MPS6734	EBC	250	0.3	40	10	2	20	2	50	10
MPSW43	EBC	200	0.3	50	30	0.4	20	2	50	10
MPS6733	EBC	200	0.3	40	10	2	20	2	50	10

TABLE 5. High-Voltage Amplifier Transistors (continued)

Device Type	Pin Out	$V_{(BR)CEO}$ Volts Min	I_C Max mA	h_{FE} Min	@ I_C mA	V_F Volts Max	$V_{CE(sat)}$ @ I_C mA	I_B mA	f_T MHz Min	@ I_C mA
PNP — TO-226AA										
BF493S	EBC	350	0.5	40	10	20	20	2	50	10
2N6520	EBC	350	0.5	30	30	3	10	1	40	10
BF493	EBC	350	0.5	40	10	0.2	20	2	50	10
MPSA92	EBC	300	0.5	40	10	0.5	20	2	50	10
2N6519	EBC	300	0.5	45	30	0.3	10	1	40	10
BF492	EBC	250	0.5	40	10	0.2	20	2	50	10
BF491	EBC	200	0.5	40	10	0.2	20	2	50	10
MPSA93	EBC	200	0.5	40	10	0.4	20	2	50	10
2N5401	EBC	150	0.6	60	10	0.2	10	1	100	10
2N5400	EBC	120	0.6	40	10	0.2	10	1	100	10
MPSL51	EBC	100	0.6	40	50	0.25	10	1	50	10
PNP — TO-226AE (1 WATT)										
BDC06	ECB	300	0.5	40	25	2	20	2	60	10
MPSW60	EBC	300	0.5	25	30	0.75	20	2	60	10
MPSW92	EBC	300	0.3	25	30	0.5	20	2	50	10
BDC08	ECB	250	0.5	40	25	2	20	2	60	10
MPSW93	EBC	200	0.3	25	30	0.5	20	2	50	10

TABLE 6. RF Transistors

The RF transistors are designed for Small Signal amplification from RF to VHF/UHF frequencies. They are also used as mixers and oscillators in the same frequency ranges. Several types are AGC characterized. The transistors are listed in order of decreasing f_T Min.

Device Type	Pin Out	$V_{(BR)CEO}$ Volts Min	I_C Max mA	h_{FE} Min	I_C	V_{CE}	f_T Typ MHz	CRE/CRB pF Max	NF Typ dB	f MHz
NPN — TO-226AA										
BF373	BEC	45	100	38	7	10	720	0.32	—	—
BF241	CEB	40	25	35	1	10	470	0.34	2.5	100
BF240	CEB	40	25	65	1	10	600	0.34	2.5	100
BF224	CEB	30	50	30	7	10	600	0.28#	2.5	100
MPSH32	BEC	30	30	27	4	5	300*	—	3.3*	45
MPSH24	BEC	30	100	30	8	10	400*	0.36	—	—
MPSH20	BEC	30	100	25	4	10	400*	—	—	—
MPSH07	EBC	30	25	20	3	10	400*	0.3	—	—
MPS3866	EBC	30	400	10	50	5	500*	—	—	—
BF371	BEC	30	100	38	7	10	720	0.23#	—	—
MPSH11	BEC	25	25	60	4	10	660*	—	—	—
MPSH10	BEC	25	100	60	4	10	1500	0.7	—	—
BF375	BEC	25	100	35	1	10	800	0.6	4	100
BF374	BEC	25	100	70	1	10	800	0.6	4	100
BF199	CEB	25	100	40	7	10	750	0.35	2.5	35
MPSH30	BEC	20	50	20	4	5	300*	—	6*	100
BF959	CEB	20	100	40	20	10	800	0.65#	3	200
BF254	CEB	20	100	65	1	10	260	0.9#	1.7	1
MPSH17	BEC	15	100	25	5	10	1600	0.9	6*	200
MPS918	EBC	15	50	20	8	10	800	1.7	6*	60
MPS5179	EBC	12	50	25	3	1	2000	—	4.5*	200
MPS3563	EBC	12	50	20	8	10	800	1.7	6*	60
MPSH04	EBC	10	30	30	1.5	10	80*	—	2*	1
PNP — TO-226AA										
MPSH55	BEC	80	100	30	1.5	10	80	—		—
MPSH55	BEC	80	100	30	1.5	10	80	—	—	—
BF506	CBE	35	50	20	3	10	600	0.25	4	200
2N5208	BEC	25	50	20	2	10	300*	—	3*	100
MPSH81	BEC	20	50	60	5	10	700	0.85	—	—

* Max

TABLE 7. High-Speed Saturated Switching Transistors

The transistors listed in this table are specially optimized for high-speed saturated switches. They are heavily gold doped and processed to provide very short switching times and low output capacitance (below 6 pF). The transistors are listed in order of decreasing turn-on time (t_{on}).

Device Type	t_{on} ns Max	& t_{off} ns Max	@ I_C mA	$V_{(BR)CEO}$ Volts Min	h_{FE} Min	@ I_C mA	$V_{CE(sat)}$ Volts Max	@ I_C mA	& I_B mA	f_T MHz Min	@ I_C mA
NPN — TO-226AA											
2N3904	70	250	10	40	100	10	0.2	10	1	300	10
2N3903	70	225	10	40	50	10	0.2	10	1	250	10
2N4400	35	255	150	40	50	150	0.4	150	15	200	20
2N4264	25	35	10	15	40	10	0.22	10	1	300	10
2N4265	25	35	10	12	100	10	0.22	10	1	300	10
MPS3646	18	28	300	15	30	30	0.2	30	3	350	30
MPS2369	12	18	10	15	40	10	0.25	10	1	500	10
PNP — TO-226AA											
MPS404A	223*	835*	10	25[1]	30	12	0.2	24	1	—	—
2N3906	70	250	10	40	100	10	0.25	10	1	250	10
2N3905	70	225	10	40	100	10	0.25	10	1	200	10
2N4402	35	255	150	40	50	150	0.4	150	15	150	20
MPS3640	25	35	50	12	30	10	0.2	10	1	500	10
MPS4258	15	20	10	12	30	50	0.15	10	1	700	10
2N5771	15	20	10	15	50	10	0.18	10	1	850	10

[1] $V_{(BR)EBO}$
* Typ

TABLE 8. Choppers

Devices are listed in decreasing ($V_{(BR)EBO}$)

Device Type	Pin Out	$V_{(BR)EBO}$ Volts Min	I_C Amp* Max	h_{FE} Min	@ I_C mA	$V_{CE(sat)}$ Volts Max	@ I_C mA	& I_B mA	f_T MHz Min	@ I_C mA
NPN — TO-226AA										
MPSA17	EBC	15	100	200	5	0.25	10	1	100	5
MPSA16	EBC	12	100	200	5	0.25	10	1	80	5
PNP — TO-226AA										
MPS404A	EBC	25	150	30	12	0.2	24	1	—	—
MPS404	EBC	12	150	30	12	0.2	24	1	—	—

TABLE 9. Industrial Transistors

These devices are special products ranges intended for use in applications which require well specified high performing devices like high quality amplifier differential input, driver stage.

NPN	PNP	Pin Out	$V_{(BR)CEO}$ (Volts)	I_C (mA) Cont	h_{FE} Min	h_{FE} Max	@ I_C (mA)	V_{CE} (Volts)	f_T Typ (MHz)	Typ (dB)	t_{on} ns Typ	t_{off} ns Typ
TO-226AA												
—	MPS2907A	EBC	60	600	100	—	10	10	200*	—	45	100
BCX59	BCX79	CBE	45	200	120	630	2	5	250	2	75	600/350
MPS2222A	—	EBC	40	600	75	—	10	10	300*	—	30	270
—	MPS2907	EBC	40	600	75	—	10	10	200*	—	45	100
MPS6531	MPS6534	EBC	40	600	90	270	100	1	250	—	30	250
BCX58	BCX78	CBE	32	200	120	630	2	5	250	2	75	600/350
MPS2222	—	EBC	30	600	75	—	10	10	250*	—	30	270
MPS6532	MPS6535	EBC	30	600	30	—	100	1	250	—	30	250

* f_T Min

TABLE 10. Telecom Transistors

These devices are special product ranges intended for use in Telecom application which require an excellent long term reliability.

Device Type	Pin Out	$V_{(BR)CEO}$ Volts	P_D mW 25°C Amb	I_C (mA) Cont	h_{FE} Min	h_{FE} Max	h_{FE} I_C (mA)	h_{FE} V_{CE} (V)	f_T Min MHz
NPN — TO-226AA									
P2N2222	CBE	30	625	600	75	—	10	10	250
P2N2222A	CBE	40	625	600	75	—	10	10	300
(1)PBF259,S	EBC	300	625	500	25	—	1	10	40
(1)PBF259R,RS	CBE	300	625	500	25	—	1	10	40
PNP — TO-226AA									
P2N2907	CBE	40	625	600	75	—	10	10	200
P2N2907A	CBE	60	625	600	100	—	10	10	200
(2)PBF493,S	EBC	300	625	500	40	—	1	10	40
(2)PBF493R,RS	CBE	300	625	500	40	—	1	10	40

(1) "S" version, h_{FE} Min 60 @ I_C = 20 mA, V_{CE} = 10 V.
(2) "S" version, h_{FE} Min 40 @ I_C = 0,1 mA, V_{CE} = 1 V.

TABLE 11. Central Collector 800 mW

The transistors listed in this table have been designed to provide power dissipation. These devices are listed in order of decreasing breakdown voltage ($V_{(BR)CEO}$).

Device Type	Pin Out	$V_{(BR)CEO}$ Volts Min	I_C Amp Cont	h_{FE} Min	@ I_C mA	$V_{CE(sat)}$ Volts Max	@ I_C mA	@ I_B mA	f_T MHz Min	@ I_C mA
NPN — TO-226AA										
BF420	ECB	300	0.1	40	25	2	20	2	60	10
BF422	ECB	250	0.1	50	25	2	20	2	60	10
BC639	ECB	80	1	40	150	0.5	500	50	60	10
BC637	ECB	60	1	40	150	0.5	500	50	60	10
BC635	ECB	45	1	40	150	0.5	500	50	60	10
BC368	ECB	20	1	60	1000	0.5	1000	100	65	10
PNP — TO-226AA										
BF421	ECB	300	0.1	40	25	2	20	2	60	10
BF423	ECB	250	0.1	50	25	2	20	2	60	10
BC640	ECB	80	1	40	150	0.5	500	50	60	10
BC639	ECB	60	1	40	150	0.5	500	50	60	10
BC636	ECB	45	1	40	150	0.5	500	50	60	10
BC369	ECB	20	1	60	1000	0.5	1000	100	65	10

TABLE 12. TO-226AE — 1 Watt High-Current

Device	Pin Out	$V_{(BR)CEO}$ Volts Min	MHz f_T Min	I_C mA	I_C Max A	h_{FE} @ Min	h_{FE} Max	I_C mA	$V_{CE(sat)}$ Max V	I_C mA	I_B mA
NPN											
BDB01D	EBC	100	50	200	1.5	40	400	100	0.7	1000	100
BDC01D	ECB	100	50	200	1.5	40	400	100	0.7	1000	100
BDB01C	EBC	80	50	200	1.5	40	400	100	0.7	1000	100
BDC01C	ECB	80	50	200	1.5	40	400	100	0.7	1000	100
MPS6717	EBC	80	50	200	0.5	80	—	50	0.5	250	10
MPSW06	EBC	80	50	200	0.5	50	—	50	0.4	250	10
BDB01B	EBC	60	50	200	1.5	40	400	100	0.7	1000	100
BDC01B	ECB	60	50	200	1.5	40	400	100	0.7	1000	100
MPSW05	EBC	60	50	200	0.5	80	—	50	0.4	250	10
MPS6716	EBC	60	50	200	0.5	80	—	50	0.5	250	10
BDB01A	EBC	45	50	200	1.5	40	400	100	0.7	1000	100
BDC01A	ECB	45	50	200	1.5	40	400	100	0.7	1000	100
MPS6715	EBC	40	50	50	1	50	—	1000	0.5	1000	100
MPSW01A	EBC	40	50	50	1	50	—	1000	0.5	1000	100
MPS6714	EBC	30	50	50	1	50	—	1000	0.5	1000	100
MPSW01	EBC	30	50	50	1	50	—	1000	0.5	1000	100

BIPOLAR DEVICES — PLASTIC-ENCAPSULATED (continued)

TABLE 12. TO-226AE — 1 Watt High-Current (continued)

Device	Pin Out	$V_{(BR)CEO}$ Volts Min	MHz f_T Min	I_C mA	I_C Max A	h_{FE} @ Min	h_{FE} Max	I_C mA	$V_{CE(sat)}$ Max V	I_C mA	I_B mA
PNP											
BDB02D	EBC	100	50	200	1.5	40	400	100	0.7	1000	100
BDC02D	ECB	100	50	200	1.5	40	400	100	0.7	1000	100
BDB02C	EBC	80	50	200	1.5	40	400	100	0.7	1000	100
BDC02C	ECB	80	50	200	1.5	40	400	100	0.7	1000	100
MPS6729	EBC	80	50	200	0.5	80	—	50	0.5	250	10
BDB02B	EBC	60	50	200	1.5	40	400	100	0.7	1000	100
BDC02B	ECB	60	50	200	1.5	40	400	100	0.7	1000	100
MPS6728	EBC	60	50	200	0.5	80	—	50	0.5	250	10
MPSW55	EBC	60	50	200	0.5	80	—	50	0.4	250	10
BDB02A	EBC	45	50	200	1.5	40	400	100	0.7	1000	100
BDC02A	ECB	45	50	200	1.5	40	400	100	0.7	1000	100
MPS6727	EBC	40	50	50	1	50	—	1000	0.5	1000	100
MPSW51A	EBC	40	50	50	1	50	—	1000	0.5	1000	100
MPS6726	EBC	30	50	50	1	50	—	1000	0.5	1000	100
MPSW51	EBC	30	50	50	1	50	—	1000	0.5	1000	100

TABLE 13. Dual Diodes

Dual diodes designed for use in low cost biasing, steering and voltage doubler applications including series, common cathode and common anode diodes.

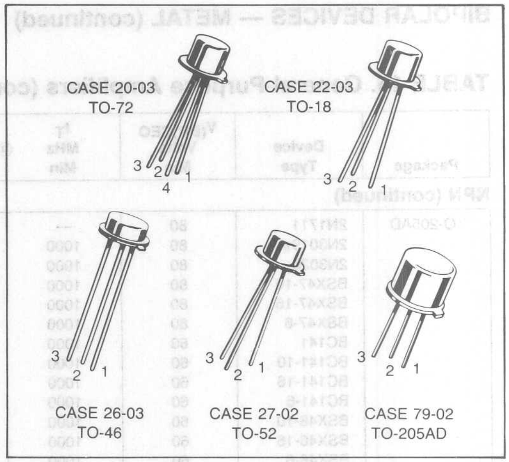
Device Type	$V_{(BR)}$ Volts Min	@ $I_{(BR)}$ μA	I_R μA Max	@ V_R Volts	V_F@ Volts Min/Max	I_F mA	C_{VR} = 0 pF Max	t_{rr} ns Max	Description
TO-226AC									
MSD6100	100	100	0.1	50	0.67/0.82	10	1.5	4	Switching
MSD6102	70	100	0.1	50	0.76/1	10	3	100	Common Cathode

TABLE 14. Voltage Reference Diode

These devices are highly reliable temperature compensated monolithic integrated circuit voltage stabilizer designed for use in television and FM radios that use variable capacitance diode tuners.

Device Type	P_D (mW)	V_Z (V) Min	V_Z (V) Max	@ I_{ZT} (mA)	$\Delta V_Z/\Delta T$ (mV/°C) Type	@ I_{ZT} (mA)	T/Min (°C)	T/Max (°C)
TO-226AC								
MVS240	625	23	25	5	−0.2	5	0	70

Metal



Motorola small-signal metal can transistors are designed for use as general-purpose amplifiers, high-speed switches, high-voltage amplifiers, low-level/low-noise amplifiers, high-frequency oscillators, choppers, and Darlingtons. These devices are manufactured in a variety of packages, i.e., TO-18, TO-205AD, TO-46, TO-52, and TO-72.

A separate listing on page 1-42 indicates those Motorola small-signal metal can transistors which are qualified to MIL-19500 high-rel requirements. Devices are available in the JAN, JANTX, JANTXV, JANS and CECC qualified versions as specified.

TABLE 15. General-Purpose Amplifiers

These transistors are designed for dc to VHF amplifier applications, general-purpose switching applications, and complementary circuitry. Devices are listed in decreasing order of $V_{(BR)CEO}$ within each package group.

Package	Device Type	$V_{(BR)CEO}$ Volts Min	f_T MHz Min	@ I_C mA	I_C mA Max	h_{FE} Min	h_{FE} Max	@ I_C mA
NPN								
TO-18	2N2896	90	1000	120	50	60	200	150
	2N3700#	80	1000	80	1.0	50	—	500
	2N2895	65	1000	120	50	40	120	150
	2N2484#	60	50	15	0.05	100	500	0.01
	2N956	50	—	70	50	40	120	150
	2N2897	45	1000	100	50	50	200	150
	2N930	45	30	30	0.5	100	300	0.01
	BC107	45	200	150	10	110	450	2.0
	BC107A	45	200	150	10	110	220	2.0
	BC107B	45	200	150	10	200	450	2.0
	BC107C	45	200	150	10	420	800	2.0
	BCY59	45	200	125	10	120	630	2.0
	BCY59-IX	45	200	125	10	250	460	2.0
	BCY59-VII	45	200	125	10	120	220	2.0
	BCY59-VIII	45	200	125	10	180	310	2.0
	BCY59-X	45	200	125	10	380	630	2.0
	2N2218#	40	800	250	20	40	120	150
	2N2221A#	40	800	250	20	40	120	150
	2N2222A#	40	800	300	20	100	300	150
	2N3946	40	200	300	10	50	150	10
	2N3947	40	200	300	10	100	300	10
	2N718	40	—	50	50	40	120	150
	BCY58	32	200	125	10	120	630	2.0
	BCY58-IX	32	200	125	10	250	460	2.0
	BCY58-VII	32	200	125	10	120	220	2.0
	BCY58-VIII	32	200	125	10	180	310	2.0
	BCY58-X	32	200	125	10	380	630	2.0
	2N2222#	30	800	250	20	100	300	150
	2N3302	30	500	250	50	100	300	150
	2N916*	25	—	300	10	50	200	10
	BC108	25	100	150	10	110	800	2.0
	BC108A	25	100	150	10	110	220	2.0
	BC108B	25	100	150	10	200	450	2.0
	BC108C	25	100	150	10	420	800	2.0
	BC109	25	100	150	10	200	800	2.0
	BC109A	25	100	150	10	110	220	2.0
	BC109B	25	100	150	10	200	450	2.0
	BC109C	25	100	150	10	420	800	2.0
	BSX51	25	200	150	10	75	225	2.0

#JAN/JANTX/JANTXV available

Package	Device Type	$V_{(BR)CEO}$ Volts Min	f_T MHz Min	@ I_C mA	I_C mA Max	h_{FE} Min	h_{FE} Max	@ I_C mA
NPN (continued)								
TO-205AD	2N1711	80	—	70	50	100	300	150
	2N3019#	80	1000	100	50	100	300	150
	2N3020	80	1000	80	50	40	120	150
	BSX47-10	80	1000	50	20	63	160	100
	BSX47-16	80	1000	50	20	100	250	100
	BSX47-6	80	1000	50	20	40	100	100
	BC141	60	1000	50	50	40	400	100
	BC141-10	60	1000	50	50	63	160	100
	BC141-16	60	1000	50	50	100	250	100
	BC141-6	60	1000	50	50	40	100	100
	BSX46-10	60	1000	50	20	63	160	100
	BSX46-16	60	1000	50	20	100	250	100
	BSX46-6	60	1000	50	20	40	100	100
	2N1613#	50	500	60	50	40	120	150
	2N2270	45	1000	100	50	50	200	150
	2N2219A#	40	800	300	20	100	300	150
	2N3053	40	700	100	50	50	250	150
	2N697	40	200	—	—	40	120	150
	BC140	40	1000	50	50	40	400	100
	BC140-10	40	1000	50	50	63	160	100
	BC140-16	40	1000	50	50	100	250	100
	BC140-6	40	1000	50	50	40	100	100
	BSX45-10	40	1000	50	20	63	160	100
	BSX45-16	40	1000	50	20	100	250	100
	BSX45-6	40	1000	50	20	40	100	100
	BFY50	35	1000	60	50	30	—	150
	2N2218#	30	800	250	20	40	120	150
	2N2219#	30	800	250	20	100	300	150
	2N3300	30	500	250	50	100	300	150
	BFY51	30	1000	50	50	40	—	150
	BFY52	20	1000	50	50	50	—	150
TO-46	2N5581**	40	800	250	20	40	120	150
	2N5582**	40	800	300	20	100	300	150
TO-52	MM3903	40	200	250	10	50	150	10
	MM3904	40	200	300	10	100	300	10
PNP								
TO-18	2N3963	80	200	40	0.5	100	450	1.0
	2N4026	80	1000	100	50	15	—	100
	2N4027	80	1000	100	50	10	—	100
	2N4028	80	1000	150	50	40	—	100
	2N4029	80	1000	150	50	25	—	100
	2N2906A#	60	600	200	50	40	120	150
	2N2907A	60	600	200	50	100	300	150
	2N3250A#	60	200	250	10	50	150	10
	2N3251A#	60	200	300	10	100	300	10
	2N3799	60	50	30	0.5	300	900	0.5
	2N3964	45	200	50	0.5	250	600	1.0
	BC177	45	200	200	10	120	460	2.0
	BC177A	45	200	200	10	120	220	2.0
	BC177B	45	200	200	10	180	460	2.0
	BC177C	45	200	200	10	380	800	2.0
	BC177VI	45	200	200	10	70	140	2.0
	BCY71	45	200	10	200	100	600	10
	BCY79-IX	45	200	180	10	250	460	2.0
	BCY79-VII	45	200	180	10	120	220	2.0
	BCY79-VIII	45	200	180	10	180	310	2.0
	BCY79-X	45	200	180	10	380	630	2.0
	2N2906#	40	600	200	50	40	120	150
	2N2907#	40	600	200	50	100	300	150
	2N3250	40	200	250	10	50	150	10
	2N3251	40	200	300	10	100	300	10
	BCY70	40	200	250	10	50	—	10

**JAN/JANTX available #JAN/JANTX/JANTXV available

TABLE 15. General-Purpose Amplifiers (continued)

Package	Device Type	$V_{(BR)CEO}$ Volts Min	f_T MHz Min	@ I_C mA	I_C mA Max	h_{FE} Min	h_{FE} Max	@ I_C mA
PNP (continued)								
TO-18	BCY78-IX	32	200	180	10	250	460	2.0
	BCY78-VII	32	200	180	10	120	220	2.0
	BCY78-VIII	32	200	180	10	180	310	2.0
	BCY78-X	32	200	180	10	380	630	2.0
	BC178	25	200	200	10	120	800	2.0
	BC178A	25	200	200	10	120	220	2.0
	BC178B	25	200	200	10	180	460	2.0
	BC178C	25	200	200	10	380	800	2.0
	BC178VI	25	200	200	10	70	140	2.0
	BCY72	25	200	250	10	50	—	10
	BC179	20	200	200	10	180	800	2.0
	BC179-VI	20	200	200	10	70	140	2.0
	BC179A	20	200	200	10	120	220	2.0
	BC179B	20	200	200	10	180	460	2.0
	BC179C	20	200	200	10	380	800	2.0
	2N869A	18	120	400	10	40	120	30
TO-205AD	MM5007	100	2000	30	50	50	250	250
	2N4031	80	1000	100	50	10	—	100
	2N4033#	80	1000	150	50	25	—	100
	2N4404	80	1000	200	50	40	120	150
	2N4405**	80	1000	200	50	100	300	150
	BSV17-10	80	1000	50	50	63	160	100
	BSV17-6	80	1000	50	50	40	100	100
	MM5006	80	2000	30	50	50	250	200
	BFX40	75	1000	100	50	85	—	100
	BFX41	75	1000	100	50	40	—	100
	2N4036	65	1000	60	50	40	140	150
	2N4037	65	1000	60	50	40	—	150
	MM4036	65	1000	60	50	20	140	150
	2N2904A#	60	600	200	50	40	120	150
	2N2905A	60	600	200	50	100	300	150
	2N4030	60	1000	100	50	15	—	100
	2N4032	60	1000	150	50	40	—	100
	BC161	60	1000	50	50	40	400	100
	BC161-10	60	1000	50	50	63	160	100
	BC161-16	60	1000	50	50	100	250	100
	BC161-6	60	1000	50	50	40	100	100
	BSV16-10	60	1000	50	50	63	160	100
	BSV16-16	60	1000	50	50	100	250	100
	BSV16-6	60	1000	50	50	40	100	100
	MM5005	60	2000	30	50	50	250	150
	2N1131A	40	600	50	50	30	90	150
	2N1132A	40	600	60	50	30	90	150
	2N2904#	40	600	200	50	40	120	150
	2N2905#	40	600	200	50	100	300	150
	BC160	40	1000	50	50	40	400	100
	BC160-10	40	1000	50	50	63	160	100
	BC160-16	40	1000	50	50	100	250	100
	BC160-6	40	1000	50	50	40	100	100
	BSV15-10	40	1000	50	50	63	160	100
	BSV15-16	40	1000	50	50	100	250	100
	BSV15-6	40	1000	50	50	40	100	100
	MM4037	40	1000	60	50	50	250	150
	2N1132	35	600	60	50	30	90	150
TO-46	2N3485A**	60	600	200	50	40	120	150
	2N3486A**	60	600	200	50	100	300	150
	2N3673	50	600	200	50	75	225	150
	2N3486	40	600	200	50	100	300	150
TO-52	MM3906	40	200	250	10	100	300	10
	MM3905	40	200	200	10	50	150	10

*JAN available **JAN/JANTX available #JAN/JANTX/JANTXV available

TABLE 16. High-Gain/Low-Noise Transistors

These transistors are characterized for high-gain and low-noise applications. Devices are listed in decreasing order of NF.

Package	Device Type	NF Wideband Typ* Max dB	$V_{(BR)CEO}$ Volts Min	I_C mA Max	h_{FE} Min	h_{FE} Max	@ I_C µA mA*	f_T MHz Min	@ I_C mA
NPN									
TO-18	2N2484#	8.0*	60	50	100	500	10	15	0.05
	2N930A	3.0	45	30	100	300	10	45	0.5
	2N930**	3.0	45	30	100	300	10	30	0.5
PNP									
TO-18	2N3962	10	60	200	100	450	1.0	40	0.5
	2N3963	10	80	200	100	450	1.0	40	0.5
	2N3965	8.0	60	200	250	600	1.0	50	0.5
	2N3964	4.0	45	200	250	600	1.0	50	0.5
	2N3798	3.5	60	50	150	450	500	30	0.5
	2N3799	2.5	60	50	300	900	500	30	0.5
TO-46	2N2604	4.0	45	30	40	120	0.01	30	0.5
	2N2605#	4.0	45	30	100	300	0.01	30	0.5

TABLE 17. High-Voltage/High-Current Amplifiers

The following table lists Motorola standard devices that have high Collector-Emitter Breakdown Voltage. Devices are listed in decreasing order of $V_{(BR)CEO}$ within each package type.

Package	Device Type	$V_{(BR)CEO}$ Volts Min	I_C mA Max	h_{FE} Min	@ I_C mA	$V_{CE(sat)}$ Volts Max	@ I_C mA	& I_B mA	f_T MHz Min	@ I_C mA
NPN										
TO-18	2N6431	300	50	50	30	0.5	20	2.0	50	10
	BSS73	300	500	40	30	0.5	50	5.0	100	20
	BSS72	250	500	40	30	0.5	50	5.0	100	20
	2N6430	200	50	50	30	0.5	20	2.0	50	10
	BSS71	200	500	40	30	0.5	50	5.0	100	20
	BC394	180	500	30	10	0.3	10	1.0	50	20
TO-205AD	2N3439#	350	1000	40	20	0.5	50	4.0	15	10
	2N5058	300	150	35	30	1.0	30	3.0	30	10
	BF259	300	100	25	30	1.0	30	6.0	110	30
	2N3440#	250	1000	40	20	0.5	50	4.0	15	10
	2N4927	250	50	20	30	2.0	30	3.0	30	10
	2N5059	250	150	30	30	1.0	30	3.0	30	10
	MM3002	250	50	20	10	—	—	—	150	10
	BF258	250	100	25	30	1.0	30	6.0	110	30
	BSS78	250	500	40	30	0.4	30	3.0	70	20
	2N4926	200	50	20	30	2.0	30	3.0	30	10
	BUY49S	200	3000	40	500	0.2	500	50	—	—
	MM3002	200	50	20	10	—	—	—	150	10
	BSS77	200	500	40	30	0.4	30	3.0	70	20
	MM3009	180	400	40	10	—	—	—	50	20
	BF357	160	100	25	30	1.0	30	6.0	110	30
	2N3500#	150	300	40	150	0.4	150	15	150	20
	2N3501#	150	300	100	150	0.4	150	15	150	20
	3N3114	150	200	30	30	1.0	50	5.0	40	30
	BSW68A	150	2000	30	500	1.0	500	150	—	—
	MM3009	150	200	20	10	—	—	—	150	10
	2N5682	120	1000	40	250	0.6	250	25	30	100
	BSW67A	120	2000	30	500	1.0	500	150	—	—
	2N3498#	100	500	40	150	0.6	300	30	150	20
	2N3499#	100	500	100	150	0.6	300	30	150	20
	2N5681	100	1000	40	250	0.6	250	25	30	100
	2N657	100	—	300	200	4.0	200	40	—	—
	MM3007	100	2500	50	250	0.35	150	15	50	50
	2N4239	80	3000	30	250	0.3	500	50	2.0	100
	MM3006	80	2500	50	200	0.35	150	15	50	50

#JAN/JANTX/JANTXV available

TABLE 17. High-Voltage High-Current Amplifiers (continued)

Package	Device Type	$V_{(BR)CEO}$ Volts Min	I_C mA Max	h_{FE} Min	@ I_C mA	$V_{CE(sat)}$ Volts Max	@ I_C mA	& I_B mA	f_T MHz Min	@ I_C mA
NPN (continued)										
TO-205AD	3N4238	60	3000	30	250	0.3	500	50	2.0	100
	MM3005	60	2500	50	150	0.35	150	15	50	50
	2N4237	40	3000	30	250	0.3	500	50	2.0	100
PNP										
TO-18	2N6433	300	500	30	30	0.5	20	20	50	10
	BSS76	300	500	35	30	0.5	50	5.0	100	20
	BSS75	250	500	35	30	0.5	50	5.0	100	20
	2N6432	200	1000	30	30	0.5	20	2.0	50	10
	BSS74	200	500	35	30	0.5	50	5.0	100	20
	BC393	180	500	50	10	0.3	10	1.0	50	20
	2N3497	120	100	40	10	0.35	10	1.0	150	20
	2N3496	80	100	40	10	0.3	10	1.0	200	20
TO-205AD	2N3494	80	100	40	10	0.3	10	1.0	200	20
	2N3495	120	100	40	10	0.35	10	1.0	150	20
	2N3635#	140	1000	100	50	0.5	50	5.0	200	30
	2N3636#	175	1000	50	50	0.5	50	5.0	150	30
	2N3637#	175	1000	100	50	0.5	50	5.0	200	30
	2N3743#	300	50	25	30	8.0	30	3.0	30	10
	2N4036	65	1000	40	150	0.65	150	15	60	50
	2N4234	40	3000	30	250	0.6	1000	125	3.0	100
	2N4235	60	3000	30	250	0.6	1000	125	3.0	100
	2N4236	80	3000	30	250	0.6	1000	125	3.0	100
	2N4928	100	100	25	10	0.5	10	1.0	100	20
	2N4929	150	500	25	10	0.5	10	1.0	100	20
	2N4930#	200	500	20	20	5.0	10	1.0	20	20
	2N4931#	250	500	20	20	5.0	10	1.0	20	20
	2N5415#	200	1000	30	50	2.5	50	5.0	15	10
	2N5416#	300	1000	30	50	2.5	50	5.0	15	10
	2N5679	100	1000	40	250	0.6	250	25	30	100
	2N5680	120	1000	40	250	0.6	250	25	30	100
	3N3634#	140	1000	50	50	0.5	50	5.0	150	30
	MM4000	100	100	20	20	0.6	10	1.0	—	—
	MM4001	150	500	20	10	0.6	10	1.0	—	—
	MM4002	200	500	20	10	5.0	10	1.0	—	—
	MM4003	250	500	20	10	5.0	10	1.0	—	—
	MM5005	60	2000	50	150	0.5	150	15	30	50
	MM5006	80	2000	50	200	0.5	150	15	30	50
	MM5007	100	2000	50	250	0.5	150	15	30	50

#JAN/JANTX/JANTXV available

TABLE 18. High-Frequency Amplifiers/Oscillators

The transistors shown are designed for use as both oscillators and amplifiers at UHF and VHF frequencies. Devices are listed in decreasing order of $V_{(BR)CEO}$ with each line.

Package	Device Type	$V_{(BR)CEO}$ Volts Min	h_{FE} Min	@ I_C mA	G_{pe} dB Min	NF dB Max	@ f MHz	f_T MHz Min	@ I_C mA	C_{obo} pF Max
NPN										
TO-18	MM1941	20	25	10	7.0	—	—	600	10	2.5
TO-72	2N918†	15	20	3.0	15	6.0	60	600	4.0	1.7
PNP										
TO-18	2N3307	35	40	2.0	17	4.5	200	300	2.0	1.3
TO-72	2N4261#	15	30	10	—	—	—	1600	10	2.5
	2N4260	15	30	10	—	—	—	2000	10	2.5

*JAN available   **JAN/JANTX available   †JAN/JANTX/JANTXV/JANS available   #JAN/JANTX/JANTXV available

The following devices are intended for use in general-purpose switching and amplifier applications. Within each package group shown, the devices are listed in order of decreasing turn-on time (t_{on}).

Package	Device Type	t_{on} ns Max	& t_{off} ns Max	@ I_C mA	$V_{(BR)CEO}$ Volts Min	I_C mA Max	h_{FE} Min	@ I_C mA	$V_{CE(sat)}$ Volts Max	@ I_C mA	@ I_B mA	f_T MHz Min	I_C mA
NPN													
TO-18	2N2540	40	40	150	30	—	100	150	0.45	150	15	250	20
	2N914**	40	40	200	15	150	12	10	0.7	200	20	300	20
	2N4014	35	60	500	50	1000	35	500	0.52	500	50	300	50
	2N4013	35	60	500	30	1000	35	500	0.42	500	50	300	50
	2N2501	15	25	300	20	—	10	500	0.3	50	5.0	350	10
	2N2369	12	18	100	15	500	20	100	0.25	10	1.0	500	10
	2N2369A†	12	18	10	15	200	40	10	0.2	10	1.0	500	10
	2N3227	12	18	100	20	50	30	100	0.25	10	1.0	500	10
	BSX20	7.0	18	100	15	500	20	10	0.25	10	1.0	400	10
TO-205AD	2N3444**	50	70	500	50	—	20	500	0.6	500	50	175	50
	2N3253**	50	70	500	40	—	25	500	0.6	500	50	175	50
	2N3735#	48	60	1000	50	1500	20	1000	0.5	500	50	250	50
	2N3734	48	60	1000	50	1500	30	1000	0.5	500	50	250	50
	2N3252	45	70	500	30	—	30	500	0.5	500	50	200	50
	2N3506#	45	90	1500	40	3000	40	1500	1.0	1500	150	60	100
	2N3507#	45	90	1500	50	3000	30	1500	1.0	1500	150	60	100
	BSX60	40	70	500	30	1000	30	500	0.5	500	50	—	—
	2N3725	35	60	500	50	2000	35	500	0.52	500	50	300	50
	2N3725A	35	60	500	30	1200	35	500	0.52	500	50	300	50
	2N3724	35	60	500	30	2000	35	500	0.42	500	50	300	50
	2N3724A	35	60	500	30	1200	35	500	0.42	500	50	300	50
	BSX59	35	60	500	45	1000	25	500	0.5	500	50	—	—
	MM5262	30	60	1000	50	2000	25	1000	0.8	1000	100	350(typ)	50
	2N5861	25	60	500	50	2000	25	500	0.5	500	50	200	50
	2N3303	15	25	1000	—	1000	20	10	0.7	1000	100	450	100
TO-46	2N3737#	48	60	1000	50	1500	20	1000	0.5	500	50	250	50
	2N3648	16	18	150	15	500	30	150	0.4	150	15	450	15
TO-52	MM1748A	10	15	10	—	150	20	10		—		600	5.0
PNP													
TO-18	2N2894	60	90	30	12	200	40	30	0.2	30	3.0	400	30
	2N869A**	50	80	30	18	200	40	30	0.2	30	3.0	400	10
	2N3546	40	30	50	12	—	25	50	0.25	50	5.0	700	10
	2N4208	15	20	10	12	200	30	10	0.15	10	1.0	700	10
	MM4258	15	20	10	12	200	30	10	0.15	10	1.0	700	10
	2N4209	15	20	10	15	200	50	10	0.6	50	5.0	850	10
TO-205AD	2N3634#	400	600	50	140	1000	50	50	0.5	50	5.0	150	30
	2N3635#	400	600	50	140	1000	100	50	0.5	50	5.0	200	30
	2N3636#	400	600	50	175	1000	50	50	0.5	50	5.0	150	30
	2N4036	110	700	150	65	1000	40	150	0.65	150	15	60	50
	2N4030	100	240(typ)	500	60	1000	15	1000	1.0	1000	100	100	50
	2N4031	100	240(typ)	500	80	1000	10	1000	0.5	500	50	100	50
	2N4032	100	240(typ)	500	60	1000	40	1000	1.0	1000	100	150	50
	2N4033#	100	240(typ)	500	80	1000	25	1000	0.5	500	50	150	50
	2N4406	75	225	1000	80	1500	20	1000	0.7	1000	100	150	50
	2N4407	75	225	1000	80	1500	30	1000	0.7	1000	100	150	50
	2N3245	55	165	500	50	1000	30	500	0.6	500	50	150	50
	2N3244	50	185	500	40	1000	50	500	0.5	500	50	175	50
	2N3467#	40	90	500	40	100	40	500	0.5	500	50	175	50
	2N3468#	40	90	500	50	1000	25	500	0.6	500	50	150	50
	2N3762#	43	115	1000	40	1500	30	1000	0.9	1000	100	180	50
	2N3763#	43	115	1000	60	1500	20	1000	0.9	1000	100	150	50
	2N4404	40	210	500	80	1000	30	500	0.5	500	50	200	50
	2N4405**	40	210	500	80	1000	50	500	0.5	500	50	200	50
	2N5022	40	90	500	—	500	25	1000	0.8	1000	100	170	50
	2N5023	40	90	500	—	500	40	1000	0.7	1000	100	200	50

**JAN/JANTX available #JAN/JANTX/JANTXV available

TABLE 23. Choppers

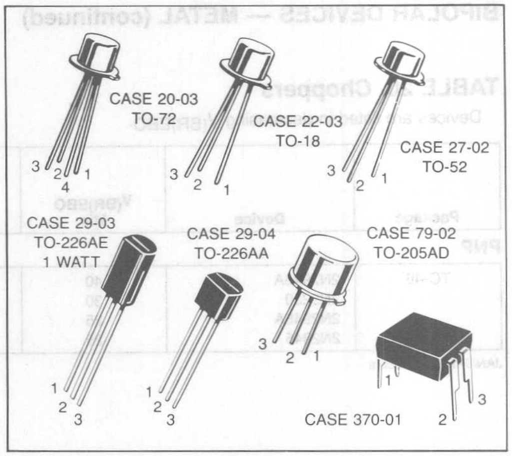
Devices are listed in decreasing $V_{(BR)EBO}$.

Package	Device	$V_{(BR)EBO}$ Min	$V_{(BR)ECO}$	$h_{FE(inv)}$ Min	Offset Voltage $V_{EC(ofs)}$ Max (mV)	On-State Resistance $r_{ec(on)}$ Max (Ω)
PNP						
TO-46	2N2946A	40	35	20	2.0	8.0
	2N5230	30	20	15	0.5	8.0
	2N2945A	25	20	30	1.0	6.0
	2N2945	25	20	4.0	1.0	35

JAN/JANTX available

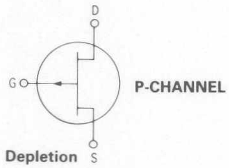
Field-Effect Transistors

Motorola offers a line of field-effect transistors that encompasses the latest technology and covers the full range of FET applications. Included here is a wide variety of junction FETs (JFETs), MOSFETs (with P- or N-channel polarity with both single and dual gates) and TMOS FETs. These FETs include devices developed for operation across the frequency range from dc to UHF in switching and amplifying applications. Package options from low cost plastic to metal TO-72 packages are available. The selector guides on the following pages are designed to emphasize those FET families and device types that, by virtue of widespread industry use, ease of manufacture and, consequently, low relative cost, merit first consideration for new equipment design.



JFETs

JFETs operate in the depletion mode. They are available in both P- and N-channel are are offered in both metal and plastic packages. Applications include general-purpose amplifiers, switches and choppers, and RF amplifiers and mixers. These devices are economical and very rugged. The drain and source are interchangeable on many typical FETs.



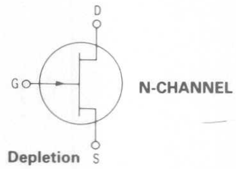


TABLE 1. Low-Frequency/Low-Noise

P-Channel JFETs

Package TO-	Device	$R_e \lvert Y_{fs} \rvert$ (mmho) Min	$R_e \lvert Y_{os} \rvert$ (µmho) Max	C_{iss} (pF) Max	C_{rss} (pF) Max	$V_{(BR)GSS}$ $V_{(BR)GDO}$ (V) Min	$V_{GS(off)}$ (V) Min	Max	I_{DSS} (mA) Min	Max
72	2N3909	1.0	100	32	16	20	0.3	7.9	0.3	15
92	MPF2608	1.0	—	17	—	30	1.0	4.0	0.9	4.5
92	2N5460	1.0	50	7.0	2.0	40	0.75	6.0	1.0	5.0
92	2N5463	1.0	75	7.0	2.0	60	0.5	4.0	1.0	5.0
72	2N3330	1.5	40	20	—	20	—	6.0	2.0	6.0
92	MPF3330	1.5	40	20	—	20	—	6.0	2.0	6.0
92	2N5461	1.5	50	7.0	2.0	40	1.0	7.5	2.0	9.0
92	2N5464	1.5	75	7.0	2.0	60	0.8	4.5	2.0	9.0
92	2N5462	2.0	50	7.0	2.0	40	1.8	9.0	4.0	16
92	2N5465	2.0	75	7.0	2.0	60	1.5	6.0	4.0	16
72	2N3909A	2.2	100	9.0	3.0	20	0.3	7.9	1.0	15

N-Channel JFETs

Package TO-	Device	$R_e \lvert Y_{fs} \rvert$ (mmho) Min	@ f (MHz)	$R_e \lvert Y_{os} \rvert$ (µmho) Max	@ f (MHz)	C_{iss} (pF) Max	C_{rss} (pF) Max	$V_{(BR)GSS}$ $V_{(BR)GDO}$ (V) Min	$V_{GS(off)}$ (V) Min	Max	I_{DSS} (mA) Min	Max
18	2N3370	0.3	30	15	30	20	3.0	40	—	3.2	0.1	0.6
92	J201	0.5	20	1.0t	20	5.0t	2.0t	40	0.3	1.5	0.2	1.0
18	2N3369	0.6	30	30	30	20	3.0	40	—	6.5	0.5	2.5
18	2N4339	0.8	15	15	15	7.0	3.0	50	0.6	1.8	0.5	1.5
92	MPF4339	0.8	15	15	15	7.0	3.0	50	0.6	1.8	0.5	1.5
18	2N3460	0.8	20	5.0	30	18	6.0	50	—	1.8	0.2	1.0
18	2N3438	0.8	20	5.0	30	18	6.0	50	—	2.3	0.2	1.0
72	2N4220	1.0	15	10	15	6.0	2.0	30	—	4.0	0.5	3.0
72	2N4220A	1.0	15	10	15	6.0	2.0	30	—	4.0	0.5	3.0

t = typical

TABLE 1. Low-Frequency/Low-Noise (continued)

N-Channel JFETs (continued)

Package TO-	Device	$R_e \lvert Y_{fs} \rvert$ (mmho) Min	@ f (MHz)	$R_e \lvert Y_{os} \rvert$ (μmho) Max	@ f (MHz)	C_{iss} (pF) Max	C_{rss} (pF) Max	$V_{(BR)GSS}$ $V_{(BR)GDO}$ (V) Min	$V_{GS(off)}$ (V) Min	$V_{GS(off)}$ (V) Max	I_{DSS} (mA) Min	I_{DSS} (mA) Max
92	J202	1.0	20	3.5^t	20	5.0^t	2.0^t	40	0.8	4.0	0.9	4.5
18	2N3368	1.0	30	80	30	20	3.0	40	—	11.5	2.0	12
72	2N5359	1.2	15	10	15	6.0	2.0	40	0.8	4.0	0.6	1.6
18	2N4340	1.3	15	30	15	7.0	3.0	50	1.0	3.0	1.2	3.6
72	2N5360	1.4	15	20	15	6.0	2.0	40	0.8	4.0	0.5	2.5
92	2N5458	1.5	15	50	15	7.0	3.0	25	1.0	7.0	2.0	9.0
72	2N5361	1.5	15	20	15	6.0	2.0	40	1.0	6.0	2.5	5.0
92	J203	1.5	20	10^t	20	5.0^t	2.0^t	40	2.0	10	4.0	20
18	2N3459	1.5	20	20	30	18	6.0	50	—	3.4	0.8	4.0
72	2N3821	1.5	15	10	15	6.0	3.0	50	—	4.0	0.5	2.5
92	MPF3821	1.5	15	10	15	6.0	3.0	50	—	4.0	0.5	2.5
18	2N3437	1.5	20	20	30	18	6.0	50	—	4.8	0.8	4.0
92	2N5457	2.0	15	50	15	7.0	3.0	25	0.5	6.0	1.0	5.0
92	2N5459	2.0	15	50	15	7.0	3.0	25	2.0	8.0	4.0	16
72	2N4221	2.0	15	20	15	6.0	2.0	30	—	6.0	2.0	6.0
92	MPF4221	2.0	15	20	15	6.0	2.0	30	—	6.0	2.0	6.0
72	2N4221A	2.0	15	20	15	6.0	2.0	30	—	6.0	2.0	6.0
72	2N3822	2.0	15	20	15	6.0	3.0	50	—	6.0	2.0	10
92	MPF3822	2.0	15	20	15	6.0	3.0	50	—	6.0	2.0	10
18	2N4341	2.0	15	60	15	7.0	3.0	50	2.0	6.0	3.0	9.0
72	2N4222	2.5	15	40	15	6.0	2.0	30	—	8.0	5.0	15
72	2N4222A	2.5	15	40	15	6.0	2.0	30	—	8.0	5.0	15
92	MPF4222A	2.5	15	40	15	6.0	2.0	30	—	8.0	5.0	15
92	2N5670	3.0	15	75	15	7.0	3.0	25	2.0	8.0	8.0	20
18	2N4398	12^t	0.001	—	—	14	3.5	40	0.5	3.0	5.0	30
72	2N4118	80	0.001	5.0	10	3.0	1.5	40	1.0	3.0	80	240
92	MPF4118	80	0.001	5.0	10	3.0	1.5	40	1.0	3.0	80	240
72	2N4118A	80	0.001	5.0	10	3.0	1.5	40	1.0	3.0	80	240
92	MPF4118A	80	0.001	5.0	10	3.0	1.5	40	1.0	3.0	80	240

t = typical

TABLE 2. High-Frequency Amplifiers

N-Channel JFETs

Package TO-	Device	$R_e \lvert Y_{fs} \rvert$ (mmho) Min	@ f (MHz)	$R_e \lvert Y_{os} \rvert$ (μmho) Max	@ f (MHz)	C_{iss} (pF) Max	C_{rss} (pF) Max	NF (dB) Max	@ RG = 1K f (MHz)	$V_{(BR)GSS}$ $V_{(BR)GDO}$ (V) Min	$V_{GS(off)}$ (V) Min	$V_{GS(off)}$ (V) Max	I_{DSS} (mA) Min	I_{DSS} (mA) Max
92	2N5669	1.6	100	100	100	7.0	3.0	2.5	100	25	1.0	6.0	4.0	10
92	MPF102	1.6	100	200	100	7.0	3.0	—	—	25	—	8.0	2.0	20
92	2N3819	1.6	100	—	—	8.0	4.0	—	—	25	—	8.0	2.0	20
92	2N5668	1.0	100	50	100	7.0	3.0	2.5	100	25	0.2	4.0	1.0	5.0
92	MPF4224	1.7	200	200	200	6.0	2.0	—	—	30	0.1	8.0	2.0	20
92	2N5484	2.5	100	75	100	5.0	1.0	3.0	100	25	0.3	3.0	1.0	5.0
92	2N5670	2.5	100	150	100	7.0	3.0	2.5	100	25	2.0	8.0	8.0	20

N-Channel JFETs (continued)

Package TO-	Device	$R_e \lvert Y_{fs} \rvert$ (mmho) Min	@ f (MHz)	$R_e \lvert Y_{os} \rvert$ (μmho) Max	@ f (MHz)	C_{iss} (pF) Max	C_{rss} (pF) Max	NF (dB) Max	@ RG = 1K f (MHz)	$V_{(BR)GSS}$ $V_{(BR)GDO}$ (V) Min	$V_{GS(off)}$ (V) Min	$V_{GS(off)}$ (V) Max	I_{DSS} (mA) Min	I_{DSS} (mA) Max
92	2N5246	2.5	400	100	400	4.5	1.0	—	—	30	0.5	4.0	1.5	7.0
92	MPF4223	2.7	200	200	200	6.0	2.0	5.0	200	30	0.1	8.0	3.0	18
92	2N5485	3.0	400	100	400	5.0	1.0	4.0	400	25	1.0	4.0	4.0	10
92	J305	3.0[t]	400	80[t]	100	3.0[t]	0.8[t]	4.0[t]	400	30	0.5	3.0	1.0	8.0
72	2N3823	3.2	200	200	200	6.0	2.0	2.5	100	30	—	8.0	4.0	20
92	2N5486	3.5	400	100	400	5.0	1.0	4.0	400	25	2.0	6.0	8.0	20
72	2N4416	40	400	100	400	4.0	0.8	4.0	400	30	2.0	6.0	5.0	15
72	2N4416A	4.0	400	100	400	4.0	0.8	4.0	400	30	2.0	6.0	5.0	15
92	2N5245	4.0	400	100	400	4.5	1.0	4.0	400	30	1.0	6.0	5.0	15
92	2N5247	4.0	400	150	400	4.5	1.0	4.0	400	30	1.5	8.0	8.0	24
92	J304	4.2[t]	400	80[t]	100	3.0[t]	0.8[t]	4.0[t]	400	30	2.0	6.0	5.0	15
52	U308	10	0.001	150	100	5.0	2.5	3.0[t]	450	25	1.0	6.0	12	60
52	U309	10	0.001	150	100	5.0	2.5	3.0[t]	450	25	1.0	4.0	12	30
52	U310	10	0.001	150	100	5.0	2.5	3.0[t]	450	25	2.5	6.0	24	60
92	J308	12[t]	100	250[t]	100	7.5	2.5	1.5[t]	100	25	1.0	6.5	12	60
92	J309	12[t]	100	250[t]	100	7.5	2.5	1.5[t]	100	25	1.0	4.0	12	30
92	J310	12[t]	100	250[t]	100	7.5	2.5	1.5[t]	100	25	2.0	6.5	24	60

t = typical

TABLE 3. Switches and Choppers

P-Channel JFETs

Package TO-	Device	$r_{ds(on)}$ (Ω) Max	@ I_D (μA)	$V_{GS(off)}$ (V) Min	$V_{GS(off)}$ (V) Max	I_{DSS} (mA) Min	I_{DSS} (mA) Max	$V_{(BR)GSS}$ $V_{(BR)GDO}$ (V) Min	C_{iss} (pF) Max	C_{rss} (pF) Max	t_{on} (ns) Max	t_{off} (ns) Max
92	MPF970	100	1.0	5.0	12	15	100	30	12	5.0	8.0	25
92	MPF971	250	1.0	1.0	7.0	2.0	80	30	12	5.0	10	120
72	2N3993	150	—	4.0	9.5	10	—	25	16	4.5	—	—
72	2N3994	300	—	1.0	5.5	2.0	—	25	16	4.5	—	—

N-Channel JFETs

Package TO-	Device	$r_{ds(on)}$ (Ω) Max	@ I_D (μA)	$V_{GS(off)}$ (V) Min	$V_{GS(off)}$ (V) Max	I_{DSS} (mA) Min	I_{DSS} (mA) Max	$V_{(BR)GSS}$ $V_{(BR)GDO}$ (V) Min	C_{iss} (pF) Max	C_{rss} (pF) Max	t_{on} (ns) Max	t_{off} (ns) Max
18	MFE2012	10	—	3.0	10	100	—	25	50	20	16	37
18	MFE2011	15	1.0	1.0	10	40	—	25	50	20	10	20
18	2N4859A	25	—	2.0	6.0	50	—	30	10	4.0	8.0	20
92	MPF4859A	25	—	2.0	6.0	50	—	30	10	4.0	8.0	20
18	2N4856A	25	—	4.0	10	50	—	40	10	4.0	8.0	20
92	MPF4856A	25	—	4.0	10	50	—	40	10	4.0	8.0	20
18	2N4856	26	—	4.0	10	50	—	40	10	8.0	9.0	25
92	MPF4856	25	—	4.0	10	50	—	40	10	8.0	9.0	25
18	2N4859	25	—	4.0	10	50	—	30	18	8.0	9.0	25
92	MPF4859	25	—	4.0	10	50	—	30	18	8.0	9.0	25
18	MFE2010	25	1.0	0.5	10	15	—	25	50	20	10	35
18	2N4391	30	1.0	4.0	10	50	150	40	14	3.5	15	20
92	MPF4391	30	1.0	4.0	10	60	130	20	10	3.5	15	20
92	2N5638	30	1.0	—	(12)	50	—	30	10	4.0	9.0	15
18	2N4091	30	1.0	5.0	10	30	—	40	16	5.0	25	40

TABLE 3. Switches and Choppers (continued)

N-Channel JFETs (continued)

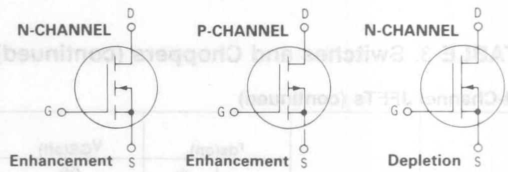
Package TO-	Device	$r_{ds(on)}$ (Ω) Max	@ I_D (μA)	$V_{GS(off)}$ (V) Min	$V_{GS(off)}$ (V) Max	I_{DSS} (mA) Min	I_{DSS} (mA) Max	$V_{(BR)GSS}$ $V_{(BR)GDO}$ (V) Min	C_{iss} (pF) Max	C_{rss} (pF) Max	t_{on} (ns) Max	t_{off} (ns) Max
92	MPF4091	30	1.0	5.0	10	30	—	40	16	5.0	25	40
92	J111	30	1.0	3.0	10	20	—	35	10^{t}	5.0^{t}	13	35
18	MFE2006	30	1.0	−5.0	−10	30	—	−30	16	5.0	20	40
18	2N3970	30	1.0	4.0	10	50	150	40	25	6.0	20	30
92	MPF3970	30	1.0	4.0	10	50	150	40	25	6.0	20	30
18	2N5857A	40	—	2.0	6.0	20	100	40	10	3.5	10	40
92	MPF4857A	40	—	2.0	6.0	20	100	40	10	3.5	10	40
18	2N4860A	40	—	2.0	6.0	20	100	30	10	3.5	10	40
92	MPF4860A	40	—	2.0	6.0	20	100	30	10	3.5	10	40
18	2N4857	40	—	2.0	6.0	20	100	40	18	8.0	10	50
92	MPF4857	40	—	2.0	6.0	20	100	40	18	8.0	10	50
18	2N4860	40	—	2.0	6.0	20	100	30	18	8.0	10	50
92	MPF4860	40	—	2.0	6.0	20	100	30	18	8.0	10	50
18	2N4092	50	1.0	2.0	7.0	15	—	40	16	5.0	35	60
92	J112	50	1.0	1.0	5.0	5.0	—	35	10^{t}	5.0^{t}	13^{t}	35^{t}
18	MFE2005	50	1.0	−2.0	−8.0	15	—	−30	16	5.0	35	60
18	2N4392	60	1.0	2.0	5.0	25	75	40	14	3.5	15	35
92	MPF4392	60	1.0	2.0	5.0	25	75	20	10	3.5	15	35
18	2N4858A	60	1.0	0.8	4.0	8.0	80	40	10	3.5	16	80
92	MPF4858A	60	1.0	0.8	4.0	8.0	80	40	10	3.5	16	80
18	2N4861A	60	—	0.8	4.0	8.0	80	30	10	3.5	16	80
92	MPF4861A	60	—	0.8	4.0	8.0	80	30	10	3.5	16	80
92	2N5639	60	1.0	—	$(8.0)^{t}$	25	—	30	10	4.0	14	30
18	2N3971	60	1.0	2.0	5.0	25	75	40	25	6.0	30	60
18	2N4858	60	—	0.8	4.0	8.0	80	40	18	8.0	20	100
92	MPF4858	60	—	0.8	4.0	8.0	80	40	18	8.0	20	100
18	2N4861	60	—	0.8	4.0	8.0	80	30	18	8.0	20	100
92	MPF4861	60	—	0.8	4.0	8.0	80	30	18	8.0	20	100
18	2N4093	80	1.0	1.0	5.0	80	—	40	16	5.0	60	80
18	MFE2004	80	1.0	−1.0	−6.0	8.0	—	−30	16	5.0	60	80
18	2N4393	100	1.0	0.5	3.0	5.0	30	40	14	3.5	15	50
92	MPF4393	100	1.0	0.5	3.0	5.0	30	20	10	3.5	15	55
92	2N5640	100	1.0	—	(6.0)	5.0	—	30	10	4.0	18	45
18	2N3972	100	1.0	0.5	3.0	5.0	30	40	25	6.0	80	100
92	MPF3972	100	1.0	0.5	3.0	5.0	30	40	25	6.0	80	100
92	J113	100	1.0	0.5	3.0	2.0	—	35	10^{t}	5.0^{t}	13^{t}	35^{t}
92	BF246	—	—	0.5	14	10	300	25	—	—	—	—
92	BF246A	35^{t}	1.0	1.5	4.0	30	80	25	—	—	—	—
92	BF246B	50^{t}	1.0	3.0	7.0	60	140	25	—	—	—	—
92	BF246C	65^{t}	1.0	5.5	12	110	250	25	—	—	—	—
92	J107	8.0	—	0.5	4.5	100	—	25	—	—	—	—
92	J108	8.0	—	3.0	10	80	—	25	—	—	—	—
92	J109	12	—	2.0	6.0	40	—	25	—	—	—	—
92	J110	18	—	0.5	4.0	10	—	25	—	—	—	—

t = typical

MOSFETs

MOSFETs are available in either depletion/enhancement or enhancement mode (in general, depletion/enhancement devices are operated in the depletion mode and are referred to as depletion devices). They are available in both N- and P-channel, and both single gate and dual gate construction. Some MOSFETs are also offered with input diode protection which reduces the chance of damage from static charge in handling.

Single Gate



Dual Gate

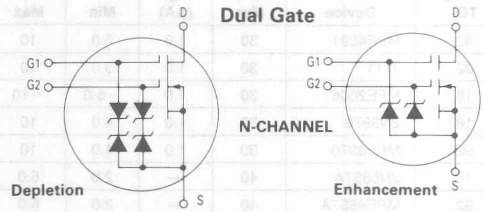


TABLE 4. Dual Gate

These devices are especially suited for RF amplifier and mixer applications in TV tuners, radio, etc. The Dual Gate construction also allows easy AGC control with very low power.

N-Channel MOSFETs

Package TO-	Device	$R_e\|Y_{fs}\|$ (mmho) Min	@ f (MHz)	$R_e\|Y_{os}\|$ (μmho) Max	@ f (MHz)	C_{iss} (pF) Max	C_{rss} (pF) Max	NF (dB) Max	NF @ RG = 1K f (MHz)	$V_{(BR)GSS}$ $V_{(BR)GDO}$ (V) Min	$V_{GS(off)}$ (V) Min	$V_{GS(off)}$ (V) Max	I_{DSS} (mA) Min	I_{DSS} (mA) Max
72	MFE521	10	0.001	—	—	4.0	0.02	3.5	200	10	0.5	2.0	5.0	20
72	3N211	17	0.001	—	—	—	0.05	3.5	200	±6.0	−0.2	−5.5	6.0	40
72	3N213	15	0.01	—	—	—	0.05	4.0	45	±6.0	−0.2	−5.5	6.0	40
72	3N203	7.0	0.001	—	—	4.3t	0.03	4.5	200	±6.0	−0.2	−5.0	3.0	11
72	3N201	8.0	0.001	—	—	4.5t	0.03	4.5	200	±6.0	−0.2	−5.0	6.0	30
72	3N202	8.0	0.001	—	—	4.3t	0.03	4.5	200	±6.0	−0.2	−5.0	6.0	30
72	MFE121	10	0.001	—	—	6.0	0.02	5.0	60	±7.0	—	−4.0	5.0	30
72	MFE131	8.0	0.001	—	—	7.0	0.05	5.0	200	±7.0	—	−4.0	3.0	30
72	3N204	10	0.001	—	—	—	0.03	5.0	400	25	−0.2	−4.0	6.0	30
72	3N205	10	0.001	—	—	—	0.03	5.0	400	25	−0.2	−4.0	6.0	30
72	3N209	10	0.001	—	—	7.0	0.03	6.0	500	±7.0	−0.1	−4.0	5.0	30

t = typical

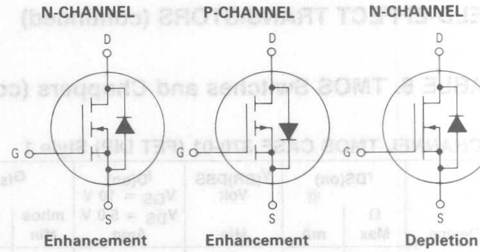
TABLE 5. Low-Frequency/Low-Noise

P-Channel MOSFETs

Package TO-	Device	$R_e\|Y_{fs}\|$ (mmho) Min	$R_e\|Y_{fs}\|$ (μmho) Max	C_{iss} (pF) Max	C_{rss} (pF) Max	$V_{(BR)DSS}$ (V) Min	$V_{GS(th)}$ (V) Min	$V_{GS(th)}$ (V) Max	I_{DSS} (mA) Min	I_{DSS} (mA) Max
72	3N155	1.0	60	5.0	1.3	−35	−1.5	−3.2	—	−1.0
72	3N156	1.0	60	5.0	1.3	−35	−3.0	−5.0	—	−1.0
72	3N157	1.0	60	5.0	1.3	−35	−1.5	−3.2	—	−1.0
72	3N158	1.0	60	5.0	1.3	−35	−3.0	−5.0	—	−1.0
72	3N158A	1.0	60	5.0	1.3	−25	−2.0	−6.0	—	−20
18	MFE823	1.0	—	6.0	1.5	−50	−3.0	−5.0	—	−0.25

N-Channel MOSFETs

Package TO-	Device	$R_e\|Y_{fs}\|$ (mmho) Min	$R_e\|Y_{fs}\|$ (μmho) Max	C_{iss} (pF) Max	C_{rss} (pF) Max	$V_{(BR)DSS}$ (V) Min	$V_{GS(th)}$ (V) Min	$V_{GS(th)}$ (V) Max	I_{DSS} (mA) Min	I_{DSS} (mA) Max
18	2N3796	0.4	1.8	7.0	0.8	25	—	−7.0	2.0	6.0
18	MFE825	0.5	—	4.0	0.7	20	—	—	1.0	25
72	2N4351	1.0	—	5.0	1.3	25	1.0	5.0	—	10
72	3N169	1.0	—	5.0	1.3	25	0.5	1.5	—	10
72	3N170	1.0	—	5.0	1.3	25	1.0	2.0	—	10
72	3N171	1.0	—	5.0	1.3	25	1.5	3.0	—	10
18	2N3797	1.5	—	8.0	0.8	25	—	−7.0	2.0	6.0



Small-Signal TMOS

TABLE 6. TMOS Switches and Choppers

N-CHANNEL TMOS TO-226AA, Style 5

Device	$r_{DS(on)}$ Ω Max	@ I_D A	$V_{GS(th)}$ V Min	$V_{GS(th)}$ V Max	$V_{(BR)DSS}$ V Min	C_{iss} pF Max	C_{rss} pF Max	t_{on} ns Max	t_{off} ns Max
VN0300L	1.2	1.0	0.8	2.5	30	100	25	30	30
2N7000	5.0	0.5	0.8	3.0	60	60	5.0	10	10
BS170	5.0	0.2	0.8	3.0	60	25 Typ	3.0 Typ	10	10
VN0610LL	5.0	0.5	0.8	2.5	60	60	5.0	10	10
VN1706L	6.0	0.5	0.8	2.0	170	125	20	16	30
VN2406L	6.0	0.5	0.8	2.0	240	125	20	16	30
BSS89	6.4	0.25	1.0	2.7	200	90	3.5	15	15
BS107A	6.4	0.25	1.0	3.0	200	70 Typ	6.0 Typ	15	15
MPF9200	6.4	0.25	1.0	4.0	200	90	10	15	15
2N7008	7.5	0.5	1.0	2.5	60	50	5.0	20	20
VN2222LL	7.5	0.5	0.6	2.5	60	60	5.0	10	10
BS108	8.5	0.1	0.3	2.0	200	90	8.0	8.0 Typ	10 Typ
VN1710L	10	0.5	0.8	2.0	170	125	20	16	50
VN2410L	10	0.5	0.8	2.0	240	125	20	16	50
MPF4150†	12	0.1	1.0	6.0	150	125	15	—	—
BS107	14	0.2	1.0	3.0	200	70 Typ	6.0 Typ	15	15
MPF350	35	0.1	1.0	4.0	350	125	20	20	20
2N7007	45	0.05	1.0	2.5	240	30	10	30	30
MPF500	50	0.1	1.0	4.0	500	125	20	20	20
MPF480	80	0.01	0.5	3.0	80	8.0	7.0	20	20
MPF481	140	0.01	0.5	3.0	180	8.0	7.0	20	20

P-CHANNEL TMOS TO-226AA, Style 5

Device	$r_{DS(on)}$ Ω Max	@ I_D A	$V_{GS(th)}$ V Min	$V_{GS(th)}$ V Max	$V_{(BR)DSS}$ V Min	C_{iss} pF Max	C_{rss} pF Max	t_{on} ns Max	t_{off} ns Max
VP0300L	2.5	1.0	2.0	4.5	30	150	60	30	30
BS170P	5.0	0.2	1.0	3.5	60	110	25	15	15
BS250	14	0.2	1.0	3.5	45	150	25	10	10

N-CHANNEL TMOS TO-226AE (1 WATT), Style 22

Device	$r_{DS(on)}$ Ω Max	@ I_D A	$V_{GS(th)}$ V Min	$V_{GS(th)}$ V Max	$V_{(BR)DSS}$ V Min	C_{iss} pF Max	C_{rss} pF Max	t_{on} ns Max	t_{off} ns Max
MPF930	1.4	1.0	1.0	3.5	35	70	18	15	15
MPF960	1.7	1.0	1.0	3.5	60	70	18	15	15
MPF6659	1.8	1.0	0.8	2.0	35	50	10	5.0	5.0
MPF990	2.0	1.0	1.0	3.5	90	70	18	15	15
MPF6660	3.0	1.0	0.8	2.0	60	50	10	5.0	5.0
MPF6661	4.0	1.0	0.8	2.0	90	50	10	5.0	5.0
MPF910	5.0	0.5	0.8	2.5	60	50	10	10	10
MPF89	6.4	0.25	1.0	2.7	200	90	3.5	15	15

P-CHANNEL TMOS TO-226AE (1 WATT), Style 22

Device	$r_{DS(on)}$ Ω Max	@ I_D A	$V_{GS(th)}$ V Min	$V_{GS(th)}$ V Max	$V_{(BR)DSS}$ V Min	C_{iss} pF Max	C_{rss} pF Max	t_{on} ns Max	t_{off} ns Max
MPF930P	1.4	1.0	1.0	3.5	35	150	50	30	30
MPF960P	1.7	1.0	1.0	3.5	60	150	50	30	30
MPF990P	2.0	1.0	1.0	3.5	90	150	50	30	30

TABLE 6. TMOS Switches and Choppers (continued)

N-CHANNEL TMOS CASE 370-01 (FET DIP) Style 1

Device	$r_{DS(on)}$ Ω Max	@ mA	$V_{(BR)DSS}$ Volt Min	$I_{D(on)}$ V_{GS} = 10 V V_{DS} = 5.0 V Amp	G_{fs} mhos Min	@ 5.0 V Amp	C_{iss} @ 25 V pF Max	C_{oss} @ 25 V pF Max	C_{rss} @ 25 V pF Max	$t_{d(on)}$ ns Max	t_r ns Max	$t_{d(off)}$ ns Max	t_f ns Max
IRFD120	0.3	600	100	1.3	0.9	0.6	600	400	100	40	70	100	70
IRFD123	0.4	600	60	1.1	0.9	0.6	600	400	100	40	70	100	70
IRFD110	0.6	800	100	1.0	0.8	0.8	200	100	25	20	25	25	20
IRFD113	0.8	800	60	0.8	0.8	0.8	200	100	25	20	25	25	20
IRFD220	0.8	400	200	0.8	0.5	0.4	600	300	80	40	60	100	60
IRFD223	1.2	400	150	0.7	0.5	0.4	600	300	80	40	60	100	60
IRFD210	1.5	600	200	0.6	0.3	0.5	150	80	25	15	25	15	15
IRFD213	2.4	300	150	0.45	0.3	0.5	150	80	25	15	25	15	15
IRFD1Z0	2.4	250	100	0.5	0.25	0.25	70	30	10	20	25	25	20
IRFD1Z3	3.2	250	60	0.4	0.25	0.25	70	30	10	20	25	25	20

P-CHANNEL TMOS CASE 370-01 (FET DIP) Style 1

Device	$r_{DS(on)}$ Ω Max	@ mA	$V_{(BR)DSS}$ Volt Min	$I_{D(on)}$ Amp	G_{fs} mhos Min	@ 5.0 V Amp	C_{iss} pF Max	C_{oss} pF Max	C_{rss} pF Max	$t_{d(on)}$ ns Max	t_r ns Max	$t_{d(off)}$ ns Max	t_f ns Max
IRFD9120	0.6	800	100	1.0	0.8	0.8	450	350	100	50	100	100	100
IRFD9123	0.8	800	60	0.8	0.8	0.8	450	350	100	50	100	100	100
IRFD9110	1.2	300	100	0.7	0.6	0.3	250	100	35	30	60	40	40
IRFD9112	1.2	300	100	0.6	0.6	0.3	250	100	35	30	60	40	40

N-CHANNEL TMOS TO-205AD, Style 6

Device	$r_{DS(on)}$ Ω Max	@ I_D A	$V_{GS(th)}$ V Min	$V_{GS(th)}$ V Max	$V_{(BR)DSS}$ V Min	C_{iss} pF Max	C_{rss} pF Max	t_{on} ns Max	t_{off} ns Max
VN0300B	1.2	1.0	0.8	2.5	30	100	25	30	30
MFE930	1.4	1.0	1.0	3.5	35	70	18	15	15
MFE960	1.7	1.0	1.0	3.5	60	70	18	15	15
2N6659	1.8	1.0	0.8	2.0	35	50	10	5.0	5.0
MFE990	2.0	1.0	1.0	3.5	90	70	18	15	15
2N6660	3.0	1.0	0.8	2.0	60	50	10	5.0	5.0
2N6661	4.0	1.0	0.8	2.0	90	50	10	5.0	5.0
MFE910	5.0	0.5	0.8	2.5	60	50	10	10	10
VN1706B	6.0	0.5	0.8	2.0	170	125	20	16	30
VN2406B	6.0	0.5	0.8	2.0	240	125	20	16	30
MFE9200††	6.4	0.25	1.0	4.0	200	90	10	15	15
VN1710B	10	0.5	0.8	2.0	170	125	20	16	57
VN2410B	10	0.5	0.8	2.0	240	125	20	16	57
MFE4150†	12	0.1	1.0	6.0	150	125	15	—	—
MFE350	35	0.1	1.0	4.0	350	125	20	20	20
MFE500	50	0.1	1.0	4.0	500	125	20	20	20

P-CHANNEL TMOS TO-205AD, Style 6

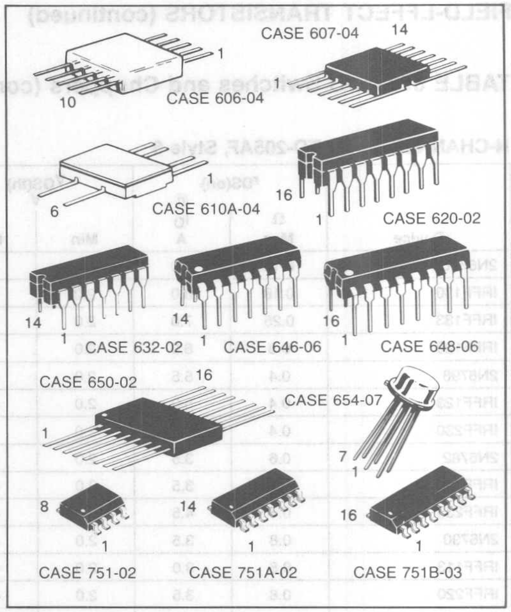
Device	$r_{DS(on)}$ Ω Max	@ I_D A	$V_{GS(th)}$ V Min	$V_{GS(th)}$ V Max	$V_{(BR)DSS}$ V Min	C_{iss} pF Max	C_{rss} pF Max	t_{on} ns Max	t_{off} ns Max
MFE930P	1.4	1.0	1.0	3.5	35	150	50	30	30
MFE960P	1.7	1.0	1.0	3.5	60	150	50	30	30
MFE990P	2.0	1.0	1.0	3.5	90	150	50	30	30
VP0300B	2.5	1.0	2.0	4.5	30	150	60	30	30

†Depletion Mode
††TO-18 — Case Style 12

N-CHANNEL TMOS TO-205AF, Style 6

Device	$r_{DS(on)}$ Ω Max	@ I_D A	$V_{GS(th)}$ V Min	Max	$V_{(BR)DSS}$ V Min	C_{iss} pF Max	C_{rss} pF Max	t_{on} ns Max	t_{off} ns Max
2N6796	0.18	8.0	2.0	4.0	100	900	150	105	85
IRFF130	0.18	8.0	2.0	4.0	100	800	150	200	250
IRFF133	0.25	7.0	2.0	4.0	60	800	150	200	250
IRFF120	0.3	6.0	2.0	4.0	100	600	100	110	170
2N6798	0.4	5.5	2.0	4.0	200	900	150	80	90
IRFF123	0.4	5.0	2.0	4.0	60	600	100	110	170
IRFF230	0.4	5.5	2.0	4.0	200	150	150	80	90
2N6782	0.6	3.5	2.0	4.0	100	200	25	40	45
IRFF110	0.6	3.5	2.0	4.0	100	200	25	45	45
IRFF233	0.6	4.5	2.0	4.0	150	800	150	80	90
2N6790	0.8	3.5	2.0	4.0	200	600	80	90	100
IRFF113	0.8	3.0	2.0	4.0	60	200	25	45	45
IRFF220	0.8	3.5	2.0	4.0	200	600	80	100	160
2N6800	1.0	3.0	2.0	4.0	400	900	80	65	90
IRFF330	1.0	3.5	2.0	4.0	400	900	80	65	90
IRFF223	1.2	3.0	2.0	4.0	150	600	80	100	160
MFE930	1.4	1.0	1.0	3.5	35	70	18	15	15
2N6784	1.5	2.25	2.0	4.0	200	200	25	35	50
2N6802	1.5	3.5	2.0	4.0	500	900	60	60	85
IRFF210	1.5	2.2	2.0	4.0	200	150	25	40	30
IRFF333	1.5	3.0	2.0	4.0	350	900	80	65	90
IRFF430	1.5	2.75	2.0	4.0	500	800	60	60	85
IRFF313	1.5	1.15	2.0	4.0	350	150	15	30	25
MFE960	1.7	1.0	1.0	3.5	60	70	18	15	15
2N6659	1.8	1.0	0.8	2.0	35	50	10	5.0	5.0
IRFF433	2.0	2.25	2.0	4.0	450	800	60	60	85
MFE960	2.0	1.0	1.0	3.5	90	70	18	15	15
IRFF213	2.4	1.8	2.0	4.0	150	150	25	40	30
2N6660	3.0	1.0	0.8	2.0	60	50	10	5.0	5.0
2N6786*	3.6	1.25	2.0	4.0	400	200	15	35	65
IRFF310	3.6	1.35	2.0	4.0	400	150	15	30	25
2N6661	4.0	1.0	0.8	2.0	90	50	10	5.0	5.0
P-CHANNEL TMOS TO-205AF, Style 6									
IRFF9120	0.6	−4.0	2.0	4.0	−100	450	100	150	200
IRFF9123	0.8	−3.5	2.0	4.0	−60	450	100	151	200

Multiple Devices



Bipolar Devices

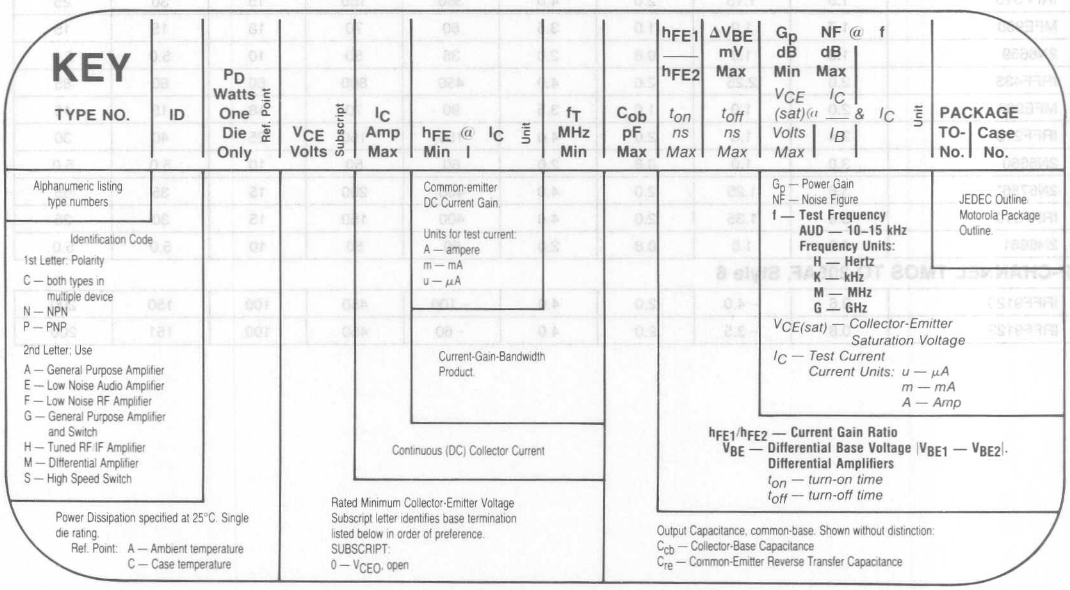
The trend in electronic system design is toward the use of integrated circuits — to reduce component cost, assembly cost, and equipment cost. But ICs still aren't all things to all people, and for those circuit designs where ICs are not available, there is a noticeable swing towards the use of multiple devices.*

Motorola is reacting to this expanding market requirement by making available a large selection of quad, dual, Darlington transistors, and diode arrays for off-the-shelf delivery. The chips used in the Quad and Dual transistors are those that have emerged as the most popular ones for discrete transistor applications. But even beyond that, Motorola offers its entire vast repertoire of discrete small-signal transistors for multiple-device packaging. For special applications where the devices in these tables might not quite fit the design requirements, special configurations can be supplied with quick turnaround time and at low premiums.

**Multiple devices, as described here, encompass two or more transistor or diode chips in a single package. Included in this definition are the Darlington transistors which consist of two interconnected devices functioning as a single-stage amplifier.*

Specification Tables

The following short form specifications include Quad and Dual bipolar transistors listed in alphanumeric order. Some columns denote two different types of data indicated by either **bold** or *italic* typeface. See key and headings for proper identification. This applies to Table 1 and 2 of this section only.



MULTIPLE DEVICES (continued)

TABLE 1. Bipolar Transistors — Quads

TYPE NO.	I_D	P_D Watts One Die Only	Ref. Point	V_{CE}- Volts	Subscript	I_C Amp Max	h_{FE} Min	@ I_C	Unit	f_T MHz Min Typ*	C_{ob} pF Max Typ*	h_{FE1}/h_{FE2} t_{on} ns Max Typ*	ΔV_{BE} mV Max t_{off} ns Max Typ*	G_p dB Min V_{CE} (sat) @ Volts Max	NF @ dB Max Typ* I_C/I_B &	f I_C	Unit	PACKAGE TO- No.	PACKAGE Case No.
MHQ918	NF	0.65	A	15	O	0.05	20	3.0	m	600	2.0				**6.0**	**60**	**M**	116	632
MHQ2222†	NG	0.65	A	40	O	0.5	100	150	m	200	8.0	25*	250*	0.4	10	150	m	116	632
MHQ2369	NS	0.5	A	15	O	0.5	40	10	m	450	4.0	9.0*	15*	0.25	10	10	m	116	632
MHQ2906	PG	0.65	A	40	O	0.6	40	150	m	200	8.0	30*	100*	0.4	10	150	m	116	632
MHQ2907†	PG	0.65	A	40	O	0.6	100	150	m	200	8.0	30*	100*	0.4	10	150	m	116	632
MHQ3467†	PS	0.9	A	40	O	1.0	20	500	m	125	25	40	90	0.5	10	500	m	116	632
MHQ3546	PS	0.5	A	12	O	0.2	30	10	m	600	6.0	0.15*	25*	0.25	10	10	m	116	632
MHQ3798	PA	0.5	A	40	O	0.05	150	0.1	m	60	4.0				**3.0***	**AUD**		116	632
MHQ4002A	NS	0.75	A	45	O	1.5	30	500	m	200	10	40	75	0.52	10	500	m	116	632
MHQ4013††	NS	0.75	A	40	O	1.5	35	500	m	200	10	35	60	0.52	10	500	m	116	632
MHQ4014	NS	0.75	A	45	O	1.5	35	500	m	200	10	35	60	0.52	10	500	m	116	632
MHQ6001	CA	0.65	A	30	O	0.5	40	150	m	200	8.0	30*	225*	0.4	10	150	m	116	632
MHQ6002	CA	0.65	A	30	O	0.5	100	150	m	200	8.0	30*	225*	0.4	10	150	m	116	632
MPQ1000	NA	0.65	A	20	O	0.5	50	10	m	175	8.0			0.5	10	150	m		646
MPQ2221	NA	0.65	A	30	O	0.5	40	150	m	200	8.0	25*	250*	0.4	10	150	m		646
MPQ2221A	NA	0.65	A	30	O	0.5	40	150	m	200	8.0	25*	250*	0.4	10	150	m		646
MPQ2222	NA	0.65	A	30	O	0.5	100	150	m	200	8.0	25*	250*	0.4	10	150	m		646
MPQ2222A	NA	0.65	A	30	O	0.5	100	150	m	200	8.0	25*	250*	0.4	10	150	m		646
MPQ2369	NS	0.5	A	15	O	0.5	40	10	m	450	4.0	9.0*	15*	0.25	10	10	m		646
MPQ2483	NA	0.625	A	40	O	0.05	150	1.0	m	50					**3.0***	**AUD**			646
MPQ2484	NA	0.625	A	40	O	0.05	300	1.0	m	50					**2.0***	**AUD**			646
MPQ2906	PA	0.65	A	40	O	0.6	40	150	m	200	8.0	30*	100*	0.4	10	150	m		646
MPQ2906A	PA	0.65	A	60	O	0.6	40	150	m	200	8.0	30*	100*	0.4	10	150	m		646
MPQ2907	PA	0.65	A	40	O	0.6	100	150	m	200	8.0	30*	100*	0.4	10	150	m		646
MPQ2907A	PA	0.65	A	60	O	0.6	100	150	m	200	8.0	30*	100*	0.4	10	150	m		646
MPQ3303	NS	0.65	A	12	O	1.0	40	300	m	400	10	15	25	0.7	10	1.0	A		646
MPQ3467	PS	0.75	A	40	O	1.0	20	500	m	125	25	40	90	0.5	10	500	m		646
MPQ3546	PA	0.5	A	12	O	0.2	30	10	m	600	6.0	15*	25*	0.25	10	10	m		646
MPQ3725†	NS	1.0	A	40	O	1.0	25	500	m	250	10	35	60	0.45	10	500	m		646
MPQ3725A	NS	1.0	A	50	O	1.0	30	500	m	200	10	3.5	60	0.45		500	m		646
MPQ3762	PS	0.75	A	40	O	1.5	35	150	m	150	15	50	120	0.55	10	500	m		646
MPQ3798	PA	0.625	A	40	O	0.05	150	0.1	m	60	4.0				**3.0***	**AUD**			646
MPQ3799	PA	0.625	A	60	O	0.05	300	0.1	m	60	4.0				**2.0***	**AUD**			646
MPQ3904	NG	0.5	A	40	O	0.2	75	10	m	250	4.0	37*	136*	0.2	10	10	m		646
MPQ3906	PG	0.5	A	40	O	0.2	75	10	m	200	4.5	43*	155*	0.25	10	10	m		646
MPQ6001	CG	0.65	A	30	O	0.5	40	150	m	200	8.0	30*	225*	0.4	10	150	m		646
MPQ6002	CG	0.65	A	30	O	0.5	100	150	m	200	8.0	30*	225*	0.4	10	150	m		646
MPQ6100	CA	0.5	A	40	O	0.05	75	1.0	m	50	4.0				**4.0***	**AUD**			646
MPQ6100A	CA	0.5	A	45	O	0.05	150	1.0	m	50	4.0				**4.0***	**AUD**			646
MPQ6501	CG	0.65	A	30	O	0.5	40	150	m	200	8.0	30*	225*	0.4	10	150	m		646
MPQ6502	CG	0.65	A	30	O	0.5	100	150	m	200	8.0	30*	225*	0.4	10	150	m		646
MPQ6600	CA	0.5	A	40	O	0.05	75	1.0	m	50	4.0				**4.0***	**AUD**			646
MPQ6600A	CA	0.5	A	45	O	0.05	150	1.0	m	50	4.0			0.25	4.0	1.0	m		646
MPQ6700	CA	0.5	A	40	O	0.2	70	10	m	200	4.5			0.25	4.0	1.0	m		646
MPQ6842	CA	0.75	A	40	O	0.5	70	10	m	300	4.5	45	150	0.15	10	0.5	m		646
MPQ7041	NA	0.75	A	150	O	0.5	25	1.0	m	50	5.0			0.5	10	20	m		646
MPQ7042	NA	0.75	A	200	O	0.5	25	1.0	m	50	5.0			0.5	10	20	m		646
MPQ7043	NA	0.75	A	250	O	0.5	25	1.0	m	50	5.0			0.5	10	20	m		646
MPQ7091	PA	0.75	A	150	O	0.5	25	1.0	m	50	5.0			0.5	10	20	m		646
MPQ7092	PA	0.75	A	200	O	0.5	25	1.0	m	50	5.0			0.5	10	20	m		646
MPQ7093	PA	0.75	A	250	O	0.5	35	10	m	50	5.0			0.5	10	20	m		646
MQ918	NA	0.55	A	15	O	0.05	50	3.0	m	600	1.7				**6.0**	**60**	**M**		607
MQ930	NA	0.4	A	45	O	0.03	150	1.0	m	260*	6.0								607
MQ982	PA	0.4	A	50	O	0.6	40	150	m	200	8.0			0.5	10	150	m		607

†H, HX, and HXV Suffixes also available.
††MHQ4013 is electrically equivalent to MHQ3725.
Some columns show 2 different types of data indicated by either **bold** or *italic* typefaces. See key and headings.

MULTIPLE DEVICES (continued)

TABLE 1. Bipolar Transistors — Quads (continued)

TYPE NO.	I_D	P_D Watts One Die Only	Ref. Point	V_{CE}- Volts	Subscript	I_C Amp Max	h_{FE} Min	@ I_C	Unit	f_T MHz Min Typ*	C_{ob} pF Max Typ*	**h_{FE1}/h_{FE2}** / *t_{on} ns Max Typ**	**ΔV_{BE} mV Max** / *t_{off} ns Max Typ**	**G_p dB Min** / *$V_{CE}(sat)$@ Volts Max*	**NF @ dB Max Typ*** / *I_C/I_B*	**f** & *I_C*	Unit	PACKAGE TO- No.	PACKAGE Case No.
MQ1120	**PA**	0.4	A	30	O	0.5	50	10	m	200	8.0			*0.1*	*10*	*10*	*m*		607
MQ1129	**NA**	0.4	A	30	O	0.5	100	10	m	200	8.0			*0.15*	*10*	*10*	*m*		607
MQ2218	**NA**	0.4	A	30	O	0.5	40	150	m	200	8.0			*0.4*	*10*	*150*	*m*		607
MQ2218A	**NA**	0.6	A	40	O	0.5	40	150	m	200	8.0			*0.4*	*10*	*150*	*m*		607
MQ2219	**NA**	0.6	A	30	O	0.5	100	150	m	200	8.0			*0.3*	*10*	*150*	*m*		607
MQ2219A	**NA**	0.4	A	30	O	0.5	100	150	m	200	8.0			*0.3*	*10*	*150*	*m*		607
MQ2369	**NS**	0.4	A	15	O	0.5	40	10	m	500	4.0	*15*	*20*	*0.25*	*10*	*10*	*m*		607
MQ2484	**NE**	0.4	A	60	O	0.03	100	10	u	260*	6.0				**3.0**	**AUD**			607
MQ2905A	**PG**	0.4	A	60	O	0.6	100	150	m	300	8.0	*42*	*130*	*0.4*	*10*	*150*	*m*		607
MQ3251	**PA**	0.4	A	40	O	0.05	100	10	m	300	6.0			*0.25*	*10*	*10*	*m*		607
MQ3467	**PS**	0.4	A	40	O	1.0	20	500	m	150	20	*40*	*110*	*0.5*	*10*	*500*	*m*		607
MQ3725	**NS**	0.4	A	40	O	1.0	50	100	m	200	10	*45*	*75*	*0.26*	*10*	*100*	*m*		607
MQ3762	**PS**	0.4	A	40	O	1.5	20	1.0	A	150	20	*40*	*110*	*1.0*	*10*	*1.0*	*A*		607
MQ3798	**PA**	0.4	A	60	O	0.05	150	100	u	450*	4.0			*0.2*	*10*	*1.0*	*m*		607
MQ6001	**CG**	0.4	A	30	O	0.5	40	150	m	200	8.0	*60*	*350*	*0.4*	*10*	*150*	*m*		607
MQ7001	**PA**	0.4	A	30	O	0.6	70	1.0	m	200	8.0			*0.4*	*10*	*150*	*m*		607
MQ7003	**NA**	0.4	A	40	O	0.05	50	10	m	200	6.0			*0.35*	*10*	*1.0*	*m*		607
MQ7004	**NA**	0.4	A	13	O	0.2	30	10	m	675*	4.0			*0.4*	*10*	*10*	*m*		607
MQ7007	**PA**	0.4	A	40	O	0.2	30	1.0	m	300	8.0			*1.0*	*10*	*50*	*m*		607
MQ7021	**CG**	0.4	A	40	O	0.05	50	10	m	200	6.0	*28**	*72**	*0.35*	*10*	*10*	*m*		607
2N5146	**PA**	0.4	A	40	O	1.5	20	1.0	A	150	20	*40*	*110*	*1.0*	*10*	*1.0*	*A*		607

Some columns show 2 different types of data indicated by either **bold** or *italic* typefaces. See key and headings.

TABLE 2. Bipolar Transistors — Duals

TYPE NO.	I_D	P_D Watts One Die Only	Ref. Point	V_{CE}- Volts	Subscript	I_C Amp Max	h_{FE} Min	@ I_C	Unit	f_T MHz Min Typ*	C_{ob} pF Max Typ*	**h_{FE1}/h_{FE2}** / *t_{on} ns Max Typ**	**ΔV_{BE} mV Max** / *t_{off} ns Max Typ**	**G_p dB Min** / *$V_{CE}(sat)$@ Volts Max*	**NF @ dB Max Typ*** / *I_C/I_B*	**f** & *I_C*	Unit	PACKAGE TO- No.	PACKAGE Case No.
BFX11	**PM**	0.4	A	45	O	0.05	80	50	m	130	8.0	0.8	5.0	0.25	20	50	m	78	654
BFX15	**NM**	0.5	A	40	O	0.5	60	100	u	50	15	0.9	5.0	1.0	10	1.0	m	78	654
BFX36	**PM**	0.4	A	60	O	0.05	100	10	u	40	6.0	0.9	3.0	0.25	20	10	m	78	654
BFY81	**NM**	0.4	A	45	O	0.03	100	100	u	60	6.0	0.8	10	0.35	10	1.0	m	78	654
MD708	**NG**	0.55	A	15	O	0.2	40	10	m	300	5.0	*35*	*75*	*0.2*	*10*	*10*	*m*		654
MD708A	**NM**	0.55	A	15	O	0.2	40	10	m	300	5.0	**0.9**	**5.0**	*0.2*	*10*	*10*	*m*		654
MD708AF	**NM**	0.35	A	15	O	0.2	40	10	m	300	5.0	**0.9**	**5.0**	*0.2*	*10*	*10*	*m*		610A
MD708B	**NM**	0.55	A	15	O	0.2	40	10	m	300	5.0	**0.8**	**10**	*0.2*	*10*	*10*	*m*		654
MD708BF	**NM**	0.35	A	15	O	0.2	40	10	m	300	5.0	**0.8**	**10**	*0.2*	*10*	*10*	*m*		610A
MD918	**NF**	0.55	A	15	O	0.05	50	3.0	m	600	1.7				**6.0**	**60**	**M**		654
MD918A	**NM**	0.55	A	15	O	0.05	50	3.0	m	600	1.7	**0.9**	**5.0**		**6.0**	**60**	**M**		654
MD918AF	**NM**	0.35	A	15	O	0.05	50	3.0	m	600	1.7	**0.9**	**5.0**		**6.0**	**60**	**M**		610A
MD918B	**NM**	0.55	A	15	O	0.05	50	3.0	m	600	1.7	**0.8**	**10**		**6.0**	**60**	**M**		654
MD918BF	**NF**	0.35	A	15	O	0.05	50	3.0	m	600	1.7				**6.0**	**60**	**M**		610A
MD982,F	**PA**	0.4	A	50	O	0.6	40	150	m	200	8.0			*0.5*	*10*	*150*	*m*		610A
MD984	**PA**	0.575	A	20	O	0.2	25	10	m	250				*0.5*	*10*	*50*	*m*		654
MD985	**CA**	0.575	A	30	O	0.5	40	150	m	200	8.0			*0.5*	*10*	*150*	*m*		654
MD986	**CA**	0.55	A	15	O	0.2	25	10	m	200	4.0			*0.3*	*10*	*10*	*m*		654
MD1120F	**NM**	0.35	A	30	O	0.5	50	10	m	200	8.0	**0.8**	**10**	*0.1*	*10*	*10*	*m*		610A
MD1121	**NM**	0.575	A	30	O	0.5	50	10	m	200	8.0	**0.9**	**10**	*0.1*	*10*	*10*	*m*		654
MD1121F	**NM**	0.35	A	30	O	0.5	50	10	m	200	8.0	**0.9**	**10**	*0.1*	*10*	*10*	*m*		654
MD1122	**NM**	0.575	A	30	O	0.5	50	10	m	200	8.0	**0.9**	**5.0**	*0.1*	*10*	*10*	*m*		654
MD1122F	**NM**	0.35	A	30	O	0.5	50	20	m	200	8.0	**0.9**	**5.0**	*0.1*	*10*	*10*	*m*		654
MD1123	**PM**	0.575	A	40	O	0.2	30	100	u	250	4.0	**0.8**	**10**	*0.25*	*10*	*10*	*m*		654

Some columns show 2 different types of data indicated by either **bold** or *italic* typefaces. See key and headings.

TABLE 2. Bipolar Transistors — Duals (continued)

TYPE NO.	I_D	P_D Watts One Die Only	Ref. Point	V_{CE}- Volts	Subscript	I_C Amp Max	h_{FE} Min	@ I_C	Unit	f_T MHz Min Typ*	C_{ob} pF Max Typ*	**h_{FE1}/h_{FE2}** / *t_{on} ns Max Typ**	**ΔV_{BE} mV Max** / *t_{off} ns Max Typ**	**G_p dB Min** / *V_{CE}(sat) @ Volts Max*	**NF dB Max Typ*** / *I_C/I_B*	@ f / & I_C	Unit	PACKAGE TO-No.	PACKAGE Case No.
MD1130	**PM**	0.575	A	40	O	0.2	100	100	u	200	4.0	**0.9**	**5.0**	*0.25*	*10*	*10*	*m*		654
MD1130F	**PM**	0.35	A	40	O	0.2	100	100	u	200	4.0	**0.9**	**5.0**	*0.25*	*10*	*10*	*m*		610A
MD1132	**NM**	0.3	A	15	O	0.05	50	1.0	m	600	1.7	**0.9**	**5.0**	*0.4*	*10*	*10*	*m*		654
MD2060F	**NM**	0.35	A	60	O	0.5	30	0.1	m	100	15	**0.9**	**5.0**	*0.1*	*8.0*	*10*	*m*		610A
MD2218	**NG**	0.575	A	30	O	0.5	40	150	m	200	8.0	*60*	*350*	*0.4*	*10*	*150*	*m*		654
MD2218A	**NG**	0.575	A	30	O	0.5	40	150	m	200	8.0	*45*	*310*	*0.3*	*10*	*150*	*m*		654
MD2218AF	**NG**	0.35	A	30	O	0.5	40	150	m	200	8.0	*45*	*310*	*0.3*	*10*	*150*	*m*		610A
MD2218F	**NG**	0.35	A	30	O	0.5	40	150	m	200	8.0	*60*	*350*	*0.4*	*10*	*150*	*m*		610A
MD2219	**NG**	0.575	A	30	O	0.5	100	150	m	200	8.0	*60*	*350*	*0.4*	*10*	*150*	*m*		654
MD2219A	**NG**	0.575	A	30	O	0.5	100	150	m	200	8.0	*45*	*310*	*0.3*	*10*	*150*	*m*		654
MD2219AF	**NG**	0.35	A	30	O	0.5	100	150	m	200	8.0	*45*	*310*	*0.3*	*10*	*150*	*m*		610A
MD2369	**NS**	0.55	A	15	O	0.5	40	10	m	500	4.0	*15*	*20*	*0.25*	*10*	*10*	*m*		654
MD2369A	**NM**	0.55	A	15	O	0.5	40	10	m	500	4.0	**0.9**	**5.0**	*0.25*	*10*	*10*	*m*		654
MD2369AF	**NM**	0.35	A	15	O	0.5	40	10	m	500	4.0	**0.9**	**5.0**	*0.25*	*10*	*10*	*m*		610A
MD2369B	**NM**	0.55	A	15	O	0.5	40	10	m	500	4.0	**0.8**	**10**	*0.25*	*10*	*10*	*m*		654
MD2369BF	**NM**	0.35	A	15	O	0.5	40	10	m	500	4.0	**0.8**	**10**	*0.25*	*10*	*10*	*m*		610A
MD2904	**PG**	0.575	A	40	O	0.6	40	150	m	200	8.0	*45*	*130*	*0.4*	*10*	*150*	*m*		654
MD2904A	**PG**	0.575	A	60	O	0.6	40	150	m	200	8.0	*45*	*130*	*0.4*	*10*	*150*	*m*		654
MD2904AF	**PG**	0.35	A	60	O	0.6	40	150	m	200	8.0	*45*	*130*	*0.4*	*10*	*150*	*m*		610A
MD2904F	**PG**	0.35	A	40	O	0.6	40	150	m	200	8.0	*45*	*130*	*0.4*	*10*	*150*	*m*		610A
MD2905	**PG**	0.575	A	40	O	0.6	100	150	m	200	8.0	*45*	*130*	*0.4*	*10*	*150*	*m*		654
MD2905A	**PG**	0.575	A	60	O	0.6	100	150	m	200	8.0	*45*	*130*	*0.4*	*10*	*150*	*m*		654
MD2905AF	**PG**	0.35	A	60	O	0.6	100	150	m	200	8.0	*45*	*130*	*0.4*	*10*	*150*	*m*		610A
MD3250	**PA**	0.575	A	40	O	0.2	50	1.0	m	200	6.0			*0.25*	*10*	*10*	*m*		654
MD3250A	**PM**	0.575	A	40	O	0.2	50	1.0	m	200	6.0	**0.9**	**5.0**	*0.25*	*10*	*10*	*m*		654
MD3250AF	**PM**	0.35	A	40	O	0.2	50	1.0	m	200	6.0	**0.9**	**5.0**	*0.25*	*10*	*10*	*m*		610A
MD3251	**PA**	0.575	A	40	O	0.2	100	1.0	m	250	6.0			*0.25*	*10*	*10*	*m*		654
MD3251A	**PM**	0.575	A	40	O	0.2	100	1.0	m	250	6.0	**0.9**	**5.0**	*0.25*	*10*	*10*	*m*		654
MD3251AF	**PM**	0.35	A	40	O	0.2	100	1.0	m	250	6.0	**0.9**	**5.0**	*0.25*	*10*	*10*	*m*		610A
MD3251F	**PA**	0.35	A	40	O	0.2	100	1.0	m	250	6.0			*0.25*	*10*	*10*	*m*		610A
MD3409	**NM**	0.575	A	30	O	0.5	50	10	m	200	8.0	**0.8**	**10**	*0.15*	*10*	*10*	*m*		654
MD3410	**NM**	0.575	A	30	O	0.5	50	10	m	200	8.0	**0.9**	**10**	*0.15*	*10*	*10*	*m*		654
MD3467	**PS**	0.6	A	40	O	1.4	20	500	m	150	20	*40*	*110*	*0.5*	*10*	*500*	*m*		654
MD3725	**NS**	0.6	A	40	O	1.0	50	100	m	200	10	*45*	*75*	*0.26*	*10*	*100*	*m*		654
MD3725F	**NS**	0.35	A	40	O	1.0	50	100	m	200	10	*45*	*75*	*0.26*	*10*	*100*	*m*		610A
MD3762	**PS**	0.6	A	40	O	1.5	20	1.0	A	150	20	*40*	*110*	*1.0*	*10*	*1.0*	*A*		654
MD3762F	**PS**	0.35	A	40	O	1.5	20	1.0	A	150	20	*40*	*110*	*1.0*	*10*	*1.0*	*A*		610A
MD5000	**PH**	0.3	A	15	O	0.05	20	3.0	m	600	1.7			**15**		**200**	**M**		654
MD5000A	**PM**	0.3	A	15	O	0.05	20	3.0	m	600	1.7	**0.9**	**5.0**	**15**		**200**	**M**		654
MD5000B	**PM**	0.3	A	15	O	0.05	20	3.0	m	600	1.7	**0.8**	**10**	**15**		**200**	**M**		654
MD6001	**CG**	0.575	A	30	O	0.5	40	150	m	200	8.0	*60*	*350*	*0.4*	*10*	*150*	*m*		654
MD6001F	**CG**	0.35	A	30	O	0.5	40	150	m	200	8.0	*60*	*350*	*0.4*	*10*	*150*	*m*		610A
MD6002	**CG**	0.575	A	30	O	0.5	100	150	m	200	8.0	*60*	*350*	*0.4*	*10*	*150*	*m*		654
MD6002F	**CG**	0.35	A	30	O	0.5	100	150	m	200	8.0	*60*	*350*	*0.4*	*10*	*150*	*m*		610A
MD6003	**CA**	0.575	A	30	O	0.5	70	150	m	200	8.0			*0.4*	*10*	*150*	*m*		654
MD6100	**CA**	0.5	A	45	O	0.05	100	0.1	m	30	4.0			*0.25*	*10*	*1.0*	*m*		654
MD6100F	**CA**	0.35	A	45	O	0.05	100	0.1	m	30	4.0			*0.25*	*10*	*10*	*m*		610A
MD7000	**NA**	0.575	A	30	O	0.5	70	150	m	200	8.0			*0.4*	*10*	*150*	*m*		654
MD7001	**PA**	0.6	A	30	O	0.6	70	150	m	200	8.0			*0.4*	*10*	*150*	*m*		654
MD7001F	**PA**	0.35	A	30	O	0.6	70	150	m	200	8.0			*0.4*	*10*	*150*	*m*		610A
MD7002	**NA**	0.575	A	40	O	0.03	40	100	u	200	6.0			*0.35*	*10*	*10*	*m*		654
MD7002A	**NM**	0.575	A	40	O	0.03	40	100	u	200	6.0	**0.75**	**25**	*0.35*	*10*	*10*	*m*		654
MD7002B	**NM**	0.575	A	40	O	0.03	40	100	u	200	6.0	**0.85**	**15**	*0.35*	*10*	*10*	*m*		654
MD7003	**NA**	0.55	A	40	O	0.05	50	10	m	200	6.0			*0.35*	*10*	*1.0*	*m*		654

Some columns show 2 different types of data indicated by either **bold** or *italic* typefaces. See key and headings.

MULTIPLE DEVICES (continued)

TABLE 2. Bipolar Transistors — Duals (continued)

TYPE NO.	I_D	P_D Watts One Die Only	Ref. Point	V_{CE}- Volts	Subscript	I_C Amp Max	h_{FE} Min	@ I_C	Unit	f_T MHz Min Typ*	C_{ob} pF Max Typ*	**h_{FE1}/h_{FE2}** *t_{on} ns Max Typ**	**ΔV_{BE} mV Max** *t_{off} ns Max Typ**	**G_p dB Min** *V_{CE} (sat) @ Volts Max*	**NF dB Max Typ*** @ *I_C/I_B*	f & I_C	Unit	PACKAGE TO- No.	PACKAGE Case No.
MD7003A	**NM**	0.55	A	40	O	0.05	50	10	m	200	6.0	**0.75**	**25**	*0.35*	*10*	*1.0*	*m*		654
MD7003AF	**NM**	0.35	A	40	O	0.05	50	10	m	200	6.0	**0.75**	**25**	*0.35*	*10*	*1.0*	*m*		610A
MD7003B	**NM**	0.55	A	40	O	0.05	50	10	m	200	6.0	**0.85**	**15**	*0.35*	*10*	*1.0*	*m*		654
MD7004	**NA**	0.55	A	13	O	0.2	30	10	m	675*	4.0			*0.4*	*10*	*10*	*m*		654
MD7005	**PA**	0.55	A	12	O	0.05	30	3.0	m	650	3.0			*0.4*	*10*	*10*	*m*		654
MD7007	**PA**	0.575	A	40	O	0.2	30	1.0	m	300	8.0			*1.0*	*10*	*50*	*m*		654
MD7007A	**PM**	0.575	A	50	O	0.2	30	1.0	m	300	8.0	**0.75**	**20**	*1.0*	*10*	*50*	*m*		654
MD7007B	**PM**	0.575	A	60	O	0.2	30	1.0	m	300	8.0	**0.85**	**10**	*1.0*	*10*	*50*	*m*		654
MD7007BF	**PM**	0.35	A	40	O	0.2	30	1.0	m	300	8.0	**0.85**	**10**	*1.0*	*10*	*50*	*m*		610A
MD7007F	**PA**	0.35	A	40	O	0.2	30	1.0	m	300	8.0			*1.0*	*10*	*50*	*m*		610A
MD7021	**CG**	0.55	A	40	O	0.05	50	10	m	200	6.0	*28**	*72**	*0.35*	*10*	*10*	*m*		654
MD7021F	**CG**	0.35	A	40	O	0.05	50	10	m	200	6.0	*28**	*72**	*0.35*	*10*	*10*	*m*		610A
MD8001	**NM**	0.575	A	40	O	0.03	100	1.0	m	260*	2.6*		**15**						654
MD8002	**NM**	0.575	A	40	O	0.03	100	1.0	m	260*	2.6*		**15**						654
MD8003	**NM**	0.575	A	40	O	0.03	100	1.0	m	260*	2.6*		**15**						654
2N2060	**NM**	0.5	A	60	O	0.5	30	100	u	60	15	**0.9**	**5.0**		**8.0**	**1000**	**H**	78	654
2N2223	**NM**	0.5	A	60	O	0.5	25	100	u	50	15	**0.8**	**15**	*1.2*	*10*	*50*	*m*	78	654
2N2223A	**NM**	0.5	A	60	O	0.5	25	100	u	50	15	**0.9**	**5.0**	*1.2*	*10*	*50*	*m*	78	654
2N2453	**NM**	0.5	A	30	O	0.05	80	10	u	60	8.0	**0.9**	**3.0**		**7.0**	**1000**	**H**	78	654
2N2453A	**NM**	0.5	A	50	O	0.05	80	10	u	60	8.0	**0.9**	**3.0**		**4.0**	**1000**	**H**	78	654
2N2480A	**NM**	0.3	A	40	O	0.5	50	1.0	m	50	18	**0.8**	**5.0**	*1.3*	*10*	*50*	*m*	78	654
2N2639	**NM**	0.3	A	45	O	0.03	50	10	u	80	8.0	**0.9**	**5.0**		**4.0**	**AUD**		78	654
2N2640	**NM**	0.3	A	45	O	0.03	50	10	u	80	8.0	**0.8**	**10**		**4.0**	**AUD**		78	654
2N2641	**NE**	0.3	A	45	O	0.03	50	10	u	80	8.0				**4.0**	**AUD**		78	654
2N2642	**NM**	0.3	A	45	O	0.03	100	10	u	80	8.0	**0.9**	**5.0**		**4.0**	**AUD**		78	654
2N2643	**NM**	0.3	A	45	O	0.03	100	10	u	80	8.0	**0.8**	**10**		**4.0**	**AUD**		78	654
2N2644	**NE**	0.3	A	45	O	0.03	100	10	u	80	8.0				**4.0**	**AUD**		78	654
2N2652	**NM**	0.3	A	60	O	0.5	50	1.0	m	60	15	**0.85**	**3.0**	*1.2*	*10*	*50*	*m*	78	654
2N2652A	**NM**	0.3	A	60	O	0.5	50	1.0	m	60	15	**0.9**	**3.0**		**8.0**	**1000**	**H**	78	654
2N2721	**NM**	0.3	A	60	O	0.04	30	0.1	m	80	6.0	**0.8**	**10**	*1.0*	*10*	*10*	*m*	78	654
2N2722	**NM**	0.3	A	45	O	0.04	50	1.0	u	100	6.0	**0.9**	**5.0**	*1.0*	*20*	*10*	*m*	78	654
2N2903	**NM**	0.6	C	30	O	0.05	125	1.0	m	60	8.0	**0.8**	**10**		**7.0**	**1000**	**H**	78	654
2N2903A	**NM**	0.6	C	30	O	0.05	125	1.0	m	60	8.0	**0.9**	**5.0**		**7.0**	**1000**	**H**	78	654
2N2913	**NE**	0.3	A	45	O	0.03	60	10	u	60	6.0				**4.0**	**AUD**			654
2N2914	**NE**	0.3	A	45	O	0.03	150	10	u	60	6.0				**3.0**	**AUD**			654
2N2915	**NM**	0.3	A	45	O	0.03	60	10	u	60	6.0	**0.9**	**5.0**		**4.0**	**AUD**			654
2N2916	**NM**	0.3	A	45	O	0.03	150	10	u	60	6.0	**0.9**	**5.0**		**3.0**	**AUD**			654
2N2917	**NM**	0.3	A	45	O	0.03	60	10	u	60	6.0	**0.8**	**10**		**4.0**	**AUD**			654
2N2918	**NM**	0.3	A	45	O	0.03	150	10	u	60	6.0	**0.8**	**10**		**3.0**	**AUD**			654
2N2919	**NM**	0.3	A	60	O	0.03	60	10	u	60	6.0	**0.9**	**5.0**		**4.0**	**AUD**			654
2N2920	**NM**	0.3	A	60	O	0.03	150	10	u	60	6.0	**0.9**	**5.0**		**3.0**	**AUD**			654
2N3043	**NM**	0.25	A	45	O	0.03	100	10	u	30	8.0	**0.9**	**5.0**		**5.0**	**AUD**			610A
2N3044	**NM**	0.25	A	45	O	0.03	100	10	u	30	8.0	**0.8**	**10**		**5.0**	**AUD**			610A
2N3045	**NE**	0.25	A	45	O	0.03	100	10	u	30	8.0				**5.0**	**AUD**			610A
2N3048	**NE**	0.25	A	45	O	0.03	50	10	u	30	8.0				**5.0**	**AUD**			610A
2N3726	**PE**	0.4	A	45	O	0.3	135	1.0	m	200	8.0	**0.9**	**5.0**		**4.0**	**1000**	**H**		654
2N3727	**PE**	0.4	A	45	O	0.3	135	1.0	m	200	8.0	**0.9**	**2.5**		**4.0**	**1000**	**H**		654
2N3806	**PE**	0.5	A	60	O	0.05	150	0.1	m	100	4.0				**7.0**	**100**	**H**		654
2N3807	**PE**	0.5	A	60	O	0.05	300	0.1	m	100	4.0				**4.0**	**100**	**H**		654
2N3808	**PM**	0.5	A	60	O	0.05	150	0.1	m	100	4.0	**0.8**	**5.0**		**7.0**	**100**	**H**		654
2N3809	**PM**	0.5	A	60	O	0.05	300	0.1	m	100	4.0	**0.8**	**5.0**		**4.0**	**100**	**H**		654
2N3810	**PM**	0.5	A	60	O	0.05	150	0.1	m	100	4.0	**0.9**	**3.0**		**7.0**	**100**	**H**		654
2N3810A	**PM**	0.5	A	60	O	0.05	150	0.1	m	100	4.0	**0.95**	**1.5**		**3.0**	**100**	**H**		654
2N3811	**PM**	0.5	A	60	O	0.05	300	0.1	m	100	4.0	**0.9**	**3.0**		**4.0**	**100**	**H**		654

Some columns show 2 different types of data indicated by either **bold** or *italic* typefaces. See key and headings.

TABLE 2. Bipolar Transistors — Duals (continued)

TYPE NO.	I_D	P_D Watts One Die Only	Ref. Point	V_{CE}- Volts	Subscript	I_C Amp Max	h_{FE} Min	@ I_C	Unit	f_T MHz Min Typ*	C_{ob} pF Max Typ*	**h_{FE1}/h_{FE2}** / *t_{on} ns Max Typ**	**ΔV_{BE} mV Max** / *t_{off} ns Max Typ**	**G_p dB Min** / *V_{CE}(sat) @ Volts Max*	**NF dB Max Typ*** @ / *I_C/I_B*	**f** & / *I_C*	Unit	PACKAGE TO- No.	PACKAGE Case No.
2N3811A	**PM**	0.5	A	60	O	0.05	300	0.1	m	100	4.0	**0.95**	**1.5**		**1.5**	**100**	**H**		654
2N3813	**PA**	0.5	A	60	O	0.05	300	0.1	m	100	4.0				**2.5**	**AUD**			610A
2N3816A	**PM**	0.5	A	60	O	0.05	150	0.1	m	100	4.0	**0.95**	**1.5**		**7.0**	**100**	**H**		610A
2N3817	**PM**	0.5	A	60	O	0.05	300	0.1	m	100	4.0	**0.9**	**3.0**		**4.0**	**100**	**H**		610A
2N3838	**CE**	0.25	A	40	O	0.6	100	150	m	200	8.0	*50*	*340*		**8.0**	**1000**	**H**		610A
2N4015	**PM**	0.4	A	60	O	0.3	135	1.0	m	200	8.0	**0.9**	**5.0**		**4.0**	**1000**	**H**		654
2N4016	**PM**	0.4	A	60	O	0.3	135	1.0	m	200	8.0	**0.9**	**2.5**		**4.0**	**1000**	**H**		654
2N4854	**CE**	0.3	A	40	O	0.6	100	150	m	200	8.0	*60*	*350*		**8.0**	**1000**	**H**		654
2N4855	**CE**	0.3	A	40	O	0.6	40	150	m	200	8.0	*60*	*350*		**8.0**	**1000**	**H**		654
2N4937	**PM**	0.6	A	40	O	0.05	50	1.0	m	300	5.0	**0.9**	**3.0**		**4.0**	**AUD**			654
2N4938	**PM**	0.6	A	40	O	0.05	50	1.0	m	300	5.0	**0.8**	**5.0**		**4.0**	**AUD**			654
2N4939	**PE**	0.6	A	40	O	0.05	50	1.0	m	300	5.0				**40**	**AUD**			654
2N4941	**PM**	0.6	A	40	O	0.05	50	1.0	m	300	5.0	**0.9**	**3.0**		**4.0**	**AUD**			610A
2N5793	**NG**	0.5	A	40	O	0.6	40	150	m	200	8.0	*45*	*310*	*0.3*	*10*	*150*	*m*		654
2N5794	**NG**	0.5	A	40	O	0.6	100	150	m	200	8.0	*45*	*310*	*0.3*	*10*	*150*	*m*		654
2N5795	**NG**	0.5	A	60	O	0.6	40	150	m	200	8.0	*47*	*140*	*0.4*	*10*	*150*	*m*		654
2N5796	**NG**	0.5	A	60	O	0.6	100	150	m	200	8.0	*47*	*140*	*0.4*	*10*	*150*	*m*		654
2N6502	**NS**	0.6	A	40	O	1.0	50	100	m	250	10	*35*	*60*	*0.3*	*10*	*100*	*m*		654

Some columns show 2 different types of data indicated by either **bold** or *italic* typefaces. See key and headings.

Surface Mount Multiples

TABLE 3. Quad Transistors

Device	$V_{(BR)CEO}$	$V_{(BR)CBO}$	h_{FE} Min	h_{FE} @ I_C	f_T Min	@ mA	Package
MMPQ2222	40	60	30	300	350*	20	SO-16
MMPQ2222A	40	75	40	500	350*	20	SO-16
MMPQ2907	40	40	30	300	350*	50	SO-16
MMPQ2907A	50	60	50	500	350*	50	SO-16
MMPQ3467	40	40	20	500	125	50	SO-16
MMPQ3725	40	60	25	500	250	50	SO-16
MMPQ3725A	50	70	30	500	200	50	SO-16
MMPQ3762	40	40	20	1000	150	50	SO-16

*Typ

FETs

TABLE 4. TMOS FETs — Quads

N-CHANNEL TMOS QUAD — CASE 646-06 (14-PIN DIP)

Device	$r_{DS(on)}$ Ω Max	@ I_D A	$V_{GS(th)}$ V Min	$V_{GS(th)}$ V Max	$V_{(BR)DSS}$ V Min	C_{iss} pF Max	C_{rss} pF Max	t_{on} ns Max	t_{off} ns Max
MFQ930P	1.4	1.0	1.0	3.5	35	70	18	15	15
MFQ960P	1.7	1.0	1.0	3.5	60	70	18	15	15
MFQ6659P	1.8	1.0	0.8	2.0	36	50	10	5.0	5.0
MFQ1000P	2.0	0.5	—	10	35	—	—	10	10
MFQ990P	2.0	1.0	1.0	3.5	90	70	18	15	15
MFQ6660P	3.0	1.0	0.8	2.0	35	50	10	5.0	5.0
MFQ6661P	4.0	1.0	0.8	2.4	90	50	16	5.0	5.0
MFQ170P	5.0	0.2	0.8	3.0	60	—	—	10	10
MFQ9200P	6.2	0.2	1.0	4.0	200	90	3.5	15	15
MFQ107AP	6.4	0.25	1.0	3.0	200	90	3.5	—	—
MFQ107P	14	0.2	1.0	3.0	200	90	3.5	—	—

N-CHANNEL TMOS QUAD — CASE 648-06 (16-PIN DIP)

Device	$r_{DS(on)}$ Ω Max	@ mA	$V_{(BR)DSS}$ Volt Min	$I_{D(on)}$ V_{GS} = 10 V V_{DS} = 5.0 V Amp	G_{fs} mhos Min	@ 5.0 V Amp	C_{iss} @ 25 V pF Max	C_{oss} @ 25 V pF Max	C_{rss} @ 25 V pF Max	$t_{d(on)}$ ns Max	t_r ns Max	$t_{d(off)}$ ns Max	t_f ns Max
IRFE110	0.6	800	100	1.0	0.8	0.8	200	100	25	20	25	25	20
IRFE113	0.8	800	60	0.8	0.8	0.8	200	100	25	20	25	25	20

P-CHANNEL TMOS QUAD — CASE 648-06 (16-PIN DIP)

IRFE9120	0.8	800	100	1.0	0.8	0.8	450	350	100	50	100	100	100
IRFE9123	0.6	800	60	0.8	0.8	0.8	450	350	100	50	100	100	100

Diode Array and Dual Diodes

Multiple diode configurations utilize monolithic structures fabricated by the planar process. They are designed to satisfy fast switching requirements as in core driver and encoding/decoding applications where their monolithic configurations offer lower cost, higher reliability and space savings. The MMAD Series in surface mount packages maximize board packing density.

TABLE 5. Diode Arrays

Device	Function	Pin Connections Package	Pin Connections Diagram No.
MAD130C	Dual 10 Diode Array	632-02	1
MAD130P	Dual 10 Diode Array	646-06	1
MMAD130	Dual 10 Diode Array	751A-02	2
MAD1103C	16 Diode Array	632-02	3
MAD1103F	16 Diode Array	606-04	4
MAD1103P	16 Diode Array	646-06	3
MMAD1103	16 Diode Array	751A-02	3
MAD1104C	Dual 8 Diode Array	632-02	5
MAD1104F	Dual 8 Diode Array	607-04	5
MAD1104P	Dual 8 Diode Array	646-06	5
MMAD1104	Dual 8 Diode Array	751A-02	5
MAD1105C	8 Diode Common Cathode Array	632-02	6
MAD1105F	8 Diode Common Cathode Array	606-04	7
MAD1105P	8 Diode Common Cathode Array	646-06	6
MMAD1105	8 Diode Common Cathode Array	751A-02	6

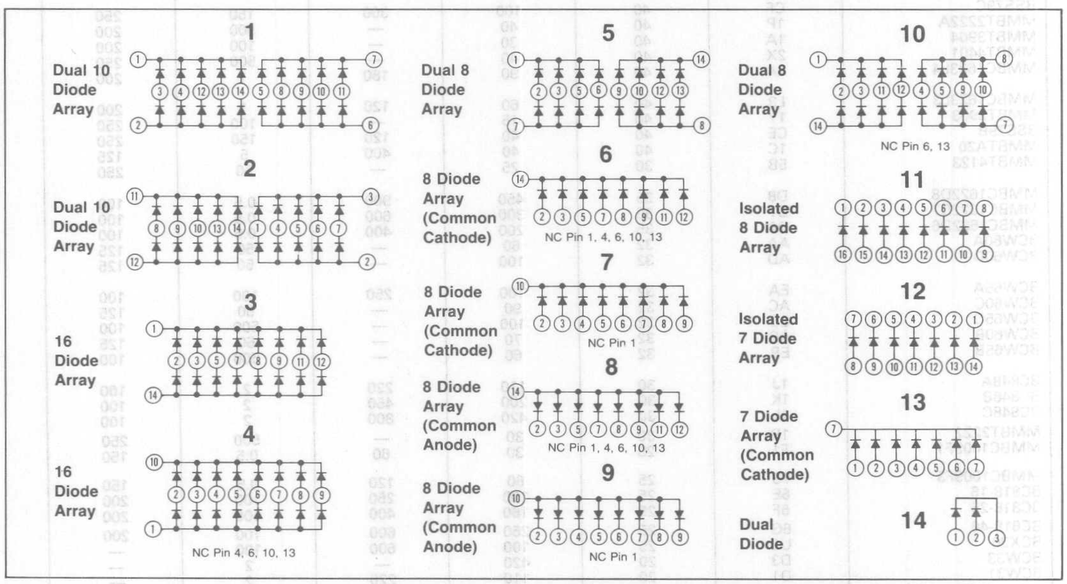
TABLE 5. Diode Arrays (continued)

Device	Function	Pin Connections Package	Diagram No.
MAD1106C	8 Diode Common Anode Array	632-02	8
MAD1106F	8 Diode Common Anode Array	606-04	9
MAD1106P	8 Diode Common Anode Array	646-06	8
MMAD1106	8 Diode Common Anode Array	751A-02	8
MAD1107C	Dual 8 Diode Array	632-02	10
MAD1107F	Dual 8 Diode Array	607-04	10
MAD1107P	Dual 8 Diode Array	646-06	10
MMAD1107	Dual 8 Diode Array	751A-02	10
MAD1108C	8 Isolated Diode Array	620-02	11
MAD1108F	8 Isolated Diode Array	650-02	11
MAD1108P	8 Isolated Diode Array	648-06	11
MMAD1108	8 Isolated Diode Array	751B-03	11
MAD1109C	7 Isolated Diode Array	632-02	12
MAD1109F	7 Isolated Diode Array	607-04	12
MAD1109P	7 Isolated Diode Array	646-06	12
MMAD1109	7 Isolated Diode Array	751A-02	12
MMAD1185	7 Diode Common Cathode Array	751-02	13

TABLE 6. Dual Diodes

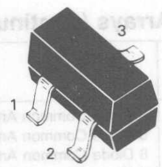
Device	Diagram No.	$V_{(BR)}$ Volts Min	@ $I_{(BR)}$ A	I_R A Max	@ V_R Volts	V_F Volts Min/Max	@ I_F mA	C @$V_R=0$ pF (Max)	t_{rr} ns Max	Package
MSD6100	14	100	100	0.1	50	0.67/0.82	10	1.5	4.0	TO-226AA
MSD6101	14	50	100	0.1	40	0.67/0.82	10	2.0	10	
MSD6102	14	70	100	0.1	50	0.67/1.0	10	3.0	100	
MSD6150	14	70	100	0.1	50	– /1.0	10	8.0	100	

Diode Array Diagrams



Surface Mount Devices

A wide variety of discrete components from Motorola's repertoire of reliability-proven semiconductor processes and geometries are available in the SOT-23 packages. Products include Bipolar and Field-Effect Transistors, Switching, Zener and Varactor Diodes. This package is capable of holding a 25 mil x 25 mil maximum die size.



CASE 318
TO-236AA
TO-236AB

SOT-23 Bipolar Transistors

TABLE 1. General-Purpose Transistors

Pinout: 1-Base, 2-Emitter, 3-Collector

Devices are listed in order of descending breakdown voltage.

Device	Marking	$V_{(BR)CEO}$	h_{FE} Min	h_{FE} Max	h_{FE} @ I_C (mA)	f_T Min (MHz)
NPN						
BC846A	1A	65	110	220	2	100
BC846B	1B	65	200	450	2	100
BSS82B	CH	60	40	120	150	100
BC817-16	6A	45	100	250	100	200
BC817-25	6B	45	160	400	100	200
BC817-40	6C	45	250	600	100	200
BC847A	1E	45	110	220	2	100
BC847B	1F	45	200	450	2	100
BC847C	1G	45	420	800	2	100
BCX70K	AK	45	100	—	50	125
BCX70J	AJ	45	90	—	50	125
BCW72	K2	45	200	450	2	—
BCX70H	AH	45	70	—	50	125
BCX70G	AG	45	60	220	50	125
MMBT930	1X	45	150	—	0.5	30
BCW71	K1	45	110	220	2	—
BCX19	U1	45	40	—	500	200
MMBC1623L7	L7	40	300	600	1	200
MMBC1623L6	L6	40	200	400	1	200
MMBC1623L5	L5	40	135	270	1	200
BSS79C	CF	40	100	300	150	250
MMBT2222A	1P	40	40	—	500	200
MMBT3904	1A	40	30	—	100	200
MMBT4401	2X	40	40	—	500	250
MMBC1623L4	L4	40	90	180	1	200
MMBC1623L3	L3	40	60	120	1	200
MMBT3903	1Y	40	15	—	100	250
BSS79B	CE	40	40	120	150	250
MMBTA20	1C	40	40	400	5	125
MMBT4123	5B	30	25	—	50	250
MMBC1622D8	D8	35	450	900	0.5	100
MMBC1622D7	D7	35	300	600	0.5	100
MMBC1622D6	D6	35	200	400	0.5	100
BCW60A	AA	32	60	—	50	125
BCW60D	AD	32	100	—	50	125
BCW65A	EA	32	100	250	100	100
BCW60C	AC	32	90	—	50	125
BCW65C	EC	32	100	—	500	100
BCW60B	AB	32	70	—	50	125
BCW65B	EB	32	60	—	500	100
BC848A	1J	30	110	220	2	100
BC848B	1K	30	200	450	2	100
BC848C	1L	30	420	800	2	100
MMBT2222	1B	30	30	—	500	250
MMBC1009F1	F1	25	30	60	0.5	150
MMBC1009F3	F3	25	60	120	0.5	150
BC818-16	6E	25	100	250	100	200
BC818-25	6F	25	160	400	100	200
BC818-40	6G	25	250	600	100	200
BCX20	U2	25	100	600	100	—
BCW33	D3	20	420	—	2	—
BCW31	D1	20	110	220	2	—

TABLE 1. General-Purpose Transistors (continued)

Device	Marking	$V_{(BR)CEO}$	h_{FE} Min	h_{FE} Max	h_{FE} @ I_C (mA)	f_T Min (MHz)
PNP						
MMBT8599	2W	80	75	—	100	150
BC856A	3A	65	125	250	2	100
BC856B	3B	65	220	475	2	100
MMBT8598	2K	60	75	—	100	150
BSS82C	CM	60	100	300	150	100
MMBT2907A	2F	60	50	—	500	200
MMBA811C8	C8	45	450	900	5	50
BC807-16	5A	45	100	250	100	200
BC807-25	5B	45	160	400	100	200
BC807-40	5C	45	250	600	100	200
BC857A	3E	45	125	250	2	100
BC857B	3F	45	220	475	2	100
BC857C	3G	45	420	800	2	100
BCX71K	BK	45	100	—	50	—
MMBA811C7	C7	45	300	600	5	50
BCX71J	BJ	45	100	—	50	—
BCW70	H2	45	215	500	2	—
MMBA811C6	C6	45	200	400	5	50
BCW68G	DG	45	60	—	500	100
MMBA811C5	C5	45	135	270	5	50
BCW69	H1	45	120	260	2	—
BCX71G	BG	45	60	—	50	—
BCW68F	DF	45	35	—	500	100
BCX17	T1	45	100	600	100	100
MMBA813S4	S4	45	100	200	50	100
MMBA813S3	S3	45	75	150	50	100
MMBA813S2	S2	45	50	100	50	100
MMBA812M7	M7	40	300	600	1	150
MMBA812M6	M6	40	200	400	1	150
MMBA812M5	M5	40	135	270	1	150
MMBT2907	2B	40	30	—	500	200
MMBT3906	2A	40	100	300	10	250
MMBT4403	2T	40	100	300	150	200
MMBA812M4	M4	40	90	180	1	150
MMBA812M3	M3	40	60	120	1	150
BSS80B	CH	40	40	120	150	200
BSS80C	CJ	40	100	30	150	200
MMBTA70	2C	40	40	400	5	125
BCW61D	BD	32	110	—	50	—
BCW61C	BC	32	100	—	50	—
BCW67C	EC	32	100	—	500	100
BCW61B	BB	32	80	—	50	—
BCW67B	DB	32	60	—	500	100
BCW61A	BA	32	60	—	50	—
BCW67A	DA	32	35	—	500	100
BC808-16	5E	25	100	250	100	200
BC808-25	5F	25	160	400	100	200
BC808-40	5G	25	250	600	100	200
BC858A	3J	30	125	250	2	100
BC858B	3K	30	220	475	2	100
BC858C	3L	30	420	800	2	100
MMBT4125	ZD	30	25	—	50	200
BCX18	T2	25	40	—	500	—
MMBTA55	AL	25	30	—	500	100
BCW30	C2	20	215	500	2	—
BCW29	C1	20	120	260	2	—

TABLE 2. Switching Transistors

Pinout: 1-Base, 2-Emitter, 3-Collector

Devices are listed in order of descending f_T.

Device	Marking	Switching Time (ns) t_{on}	t_{off}	$V_{(BR)CEO}$	h_{FE} Min	Max	@ I_C (mA)	f_T Min (MHz)
NPN								
MMBT2369	1J	12	18	15	20	—	100	—
BSV52	B2	12	18	12	40	120	10	400
MMBT2222	1B	35	385	30	30	—	500	250
MMBT2222A	1P	35	385	40	40	—	500	200
MMBT4401	2X	35	255	40	40	—	500	250
MMBT3903	1Y	70	225	40	15	—	100	250
MMBT3904	1A	70	250	40	30	—	100	200
PNP								
MMBT3638A	BN	75	170	25	20	—	300	—
MMBT3638	AM	75	170	25	20	—	300	—
MMBT3640	2J	25	35	12	20	—	50	500
MMBT4403	2T	35	225	40	90	180	1	150
MMBT2907	2B	45	100	40	30	—	500	200
MMBT2907A	2F	45	100	60	50	—	500	200
MMBT3906	2A	70	300	40	100	300	10	250

TABLE 3. VHF/UHF Amplifiers, Mixers, Oscillators

Pinout: 1-Base, 2-Emitter, 3-Collector

Device	Marking	$V_{(BR)CEO}$	C_{ob} Max (pF)	f_T Min (GHz)	@ I_C (mA)
NPN					
MMBT3960A	1T	8	2	1.6	30
MMBT3960	15	3	2	1.6	30
MMBTH10	3E	25	0.7	0.65	4
MMBC1321Q3	Q3	25	1.8	0.6	2
MMBC1321Q4	Q4	25	1.8	0.6	2
MMBC1321Q5	Q5	25	1.8	0.6	2
MMBT918	3B	15	1.7	0.6	4
MMBTH24	3A	30	0.36	0.4	8
PNP					
MMBTH81	3D	20	0.85	0.6	5

TABLE 4. Choppers

Pinout: 1-Base, 2-Emitter, 3-Collector

Device	Marking	$V_{(BR)EBO}$	$V_{(BR)CEO}$	h_{FE} Min	Max	@ I_C (mA)
PNP						
MMBT404	2M	12	24	30	400	12
MMBT404A	2N	25	35	30	400	12

TABLE 5. Darlingtons

Pinout: 1-Base, 2-Emitter, 3-Collector

Devices are listed in order of descending h_{FE}.

Device	Marking	$V_{(BR)CEO}$	$V_{CE(sat)}$ Max (V)	h_{FE} Min	h_{FE} Max	h_{FE} @ I_C (mA)
NPN						
MMBTA14	1N	30	1.5	20K	—	100
MMBT6427	1V	40	1.5	14K	140K	500
MMBTA13	1M	30	1.5	10K	—	100
PNP						
MMBTA64	2V	30	1.5	20K	—	100
MMBTA63	2U	30	1.5	10K	—	100

TABLE 6. Low-Noise Transistors

Pinout: 1-Base, 2-Emitter, 3-Collector

Devices are listed in order of ascending NF.

Device	Marking	NF Typ (dB)	$V_{(BR)CEO}$	h_{FE} Min	h_{FE} Max	h_{FE} @ I_C (mA)	f_T Min (MHz)
NPN							
MMBT5088	1Q	1	30	300	—	10	50
MMBT5089	1R	1	30	400	—	10	50
MMBT2484	1U	3	60	—	800	10	15
MMBT6428	1K	3	50	250	—	10	100
MMBT6429	1L	3	45	500	—	10	100
PNP							
MMBT5086	2P	1	50	150	—	10	40
MMBT5087	2Q	1	50	250	—	10	40
BC849B	2B	4*	30	200	450	2	100
BC849C	2C	4*	30	420	800	2	100
BC850B	2F	4*	45	200	450	2	100
BC850C	2G	4*	45	420	800	2	100
BC859A	4A	4*	30	100	220	2	100
BC859B	4B	4*	30	200	450	2	100
BC859C	4C	4*	30	420	800	2	100
BC860A	4E	4*	45	100	220	2	100
BC860B	4F	4*	45	200	450	2	100
BC860C	4G	4*	45	420	800	2	100

*Max

TABLE 7. High-Voltage Transistors

Pinout: 1-Base, 2-Emitter, 3-Collector

Devices are listed in order of descending breakdown voltage.

Device	Marking	$V_{(BR)CEO}$	h_{FE} Min	h_{FE} Max	h_{FE} @ I_C (mA)	f_T Min (MHz)
NPN						
MMBT6517	1Z	350	15	—	100	40
MMBTA42	1D	300	40	—	30	50
MMBTA43	1E	200	40	—	30	50
MMBC1654N5	N5	160	50	130	15	120
MMBC1654N6	N6	160	100	220	15	120
MMBC1654N7	N7	160	150	330	15	120
MMBT5550	1F	160	30	—	50	100
MMBT5551	G1	160	30	—	50	100
PNP						
MMBT6520	2Z	350	15	—	100	40
MMBTA92	2D	300	25	—	30	50
MMBTA93	2E	200	25	—	30	50
MMBT5401	2L	150	50	—	50	100

TABLE 8. Drivers

Pinout: 1-Base, 2-Emitter, 3-Collector

Device	Marking	$V_{(BR)CEO}$	h_{FE} Min	h_{FE} Max	h_{FE} @ I_C (mA)	f_T Min (MHz)
NPN						
MMBTA06	1G	80	50	—	100	100
BSS64	AM	80	20	80	4	50
MMBTA05	1H	60	50	—	100	100
PNP						
BSS63	BM	100	30	—	25	50
MMBTA55	2H	60	50	—	100	50
MMBTA56	2G	80	50	—	100	50

TABLE 9. RF Transistors

Pinout: 1-Base, 2-Emitter, 3-Collector

Devices are listed in order of descending f_T.

Device	Marking	f_T Typ (GHz)	f_T I_C (mA)	f_T V_{CE} (V)	NF Typ (dB)	NF @ I_C (mA)	NF V_{CE} (V)	MAG Typ (dB)	MAG @ I_C (mA)	MAG V_{CE} (V)	f (MHz)
NPN											
MMBR571	7X	8	50	10	2	5	6	16.5*	5	6	500
MMBR911	7P	6	30	10	2	10	10	17*	10	5	500
MMBR930	7C	5.5	30	5	1.9	2	5	11	30	5	500
BFR92	P1	3	14	10	3	3	1.5	—	—	—	500
BFR93	R1	3	30	5	2.5	2	5	—	—	—	30
MMBR931	7D	3.5	1	1	4.3	0.5	1	10	1	1	1000
MMBR2060	7E	2.5	20	1	2	1.5	10	13	20	10	450
MMBR5179	7H	1.5	5	6	4	1.5	6	11	5	6	450
MMBR920	7B	4.5	14	10	2.4	2	10	15	2	10	500
MMBR901	7A	4	15	10	1.9	5	6	16	5	6	1000
MMBR941	7Y	8	15	6	1.7	5	6	12.5	5	6	2000
MMBR951	7Z	7.5	30	6	1.7	5	6	12.5	5	6	2000
MMBR5031	7G	2	5	6	1.9	1	6	17	1	6	450
MMBR2857	7K	1.2	4	10	3	1.5	6	12.5	1.5	6	450
BFS17	E1	1	2	5	5	2	5	—	—	—	30
PNP											
MMBR536	7R	5.5	20	5	4.5	10	5	—	—	—	500
MMBR4957	7F	2	2	10	3	2	10	17	2	10	450

*GNF

SOT-23 Field Effect Transistors (JFETs)

TABLE 10. RF JFETs

Pinout: 1-Drain, 2-Source, 3-Gate

Device	Marking	NF Typ (dB)	NF f (MHz)	Y_{fs} Min (mmhos)	Y_{fs} Max (mmhos)	V_{DS} (V)	$V_{(BR)GSS}$
N-CHANNEL							
MMBFU310	6C	1.5	1	10	18	10	−25
MMBF102	—	3**	—	2	7.5	15	−25
MMBF108*	—	3**	100	2	7.5	15	−25
MMBF112	TV	3**	—	1	7.5	10	−25
MMBF5484	6B	2	100	3	6	15	−25
MMBF5485*	—	2	100	3.5	7	15	−25
MMBF5486	6H	2	100	4	8	15	−25
MMBF4416	6A	2	100	4.5	7.5	15	−30
MMBFJ310	6T	4	450	8	18	10	−25

**Max

TABLE 11. General-Purpose FETs

Pinout: 1-Drain, 2-Source, 3-Gate

Device	Marking	$V_{(BR)GSS}$	Y_{fs} Min (mmhos)	Y_{fs} Max (mmhos)	V_{DS} (V)	I_{DSS} Min (mA)	I_{DSS} Max (mA)
N-CHANNEL							
MMBF5457	6D	25	1	5	15	1	5
MMBF5459	6L	25	2	6	15	4	16
P-CHANNEL							
MMBF5460	6E	−40	1	4	−15	1	5

TABLE 12. Chopper/Switches, JFETs

Pinout: 1-Drain, 2-Source, 3-Gate

Device	Marking	$r_{DS(on)}$ Max (Ohms)	t_{off} Max (ns)	$V_{(BR)GSS}$	$V_{GS(off)}$ Min (V)	$V_{GS(off)}$ Max (V)	I_{DSS} Min (mA)	I_{DSS} Max (mA)
N-CHANNEL								
MMBF4391	6J	30	20	30	−4	−10	50	150
BSR56	M4	25	25	40	−4	−10	50	—
MMBF4860	6F	40	50	30	−2	−6	20	100
BSR57	M5	40	50	40	−2	−6	20	100
MMBF4392	6K	60	35	30	−2	−5	25	75
BSR58	M6	60	100	40	−0.8	−4	8	80
MMBF4393	6G	100	50	30	−0.5	−3	5	30
P-CHANNEL								
MMBFJ175	6W	125	30(t)	−30	3	6	−7	−60
MMBFJ177	6Y	300	45(t)	−30	0.8	2.5	−1.5	−20

TABLE 13. TMOS FETs

Pinout: 1-Gate, 2-Source, 3-Drain

Device	Marking	$r_{DS(on)}$ Ohm	$r_{DS(on)}$ mA	V_{DSS}	$V_{GS(th)}$ Min (V)	$V_{GS(th)}$ Max (V)	Switching Time t_{on} ns	Switching Time t_{off} ns
N-CHANNEL								
MMBF170	6Z	5	200	60	0.8	3	10	10
BSS123	SA	6	100	100	0.8	2.8	20	40
2N7002	702	7.5	500	60	1	2.5	20	20

SOT-23 Switching Diodes

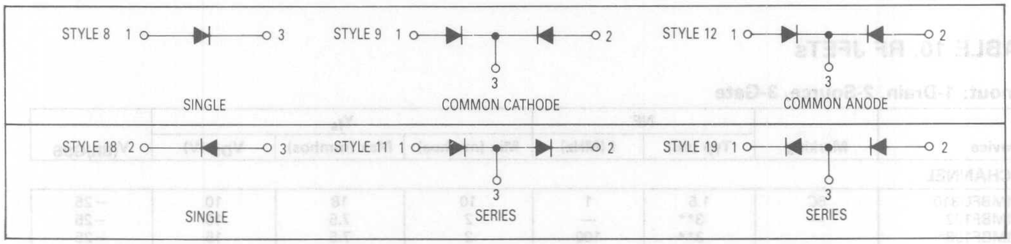


TABLE 14. General-Purpose Diodes

Device	Marking	$V_{(BR)R}$ Min (V)	$V_{(BR)R}$ @ I_{BR} (μA)	I_R Max (μA)	I_R @ V_R (V)	V_F Min (V)	V_F Max (V)	V_F @ I_F (mA)	C_T Max (pF)	t_{rr} Max (ns)	Pin Out Case Style
SINGLES											
MMBD6050X	5AX	70	100	0.1	50	0.85	1.1	100	2.5	15	8
MMBD914X	5DX	100	100	5	75		1	10	4	15	8
MBAS16	A6X	75	100	1	75		1.3	100	2	15	8
MBAL99	TFX	70	10	2.5	70		1.1	50	1.5	15	18
DUALS											
MBAV70	A4X	70	100	5	70		1.1	50	1.5	15	9
MBAW56	A1X	70	100	2.5	70		1.1	50	1.5	15	12
MBAV99	A7X	70	100	2.5	70		1.1	50	1.5	15	11
MBAV74	JAX	50	5	0.1	50		1	100	2		9
MMBD2835X	A3X	35	100	0.1	30		1	10	4	15	12
MMBD2836X	A2X	75	100	0.1	50		1	10	4	15	12
MMBD2837X	A5X	35	100	0.1	30		1	10	4	15	9
MMBD2838X	A6X	75	100	0.1	50		1	10	4	15	9
MMBD6100	5B	70	100	0.1	50	0.85	1.1	100	2.5	15	9
MMBD7000	5C	100	100	0.3	50	0.75	1.1	100	1.5	15	11

TABLE 15. Mixer and Detector Diodes

Pin Diodes are designed for VHF Band and General Purpose Switching. Hot Carrier Diodes are ideal for VHF, UHF applications.

Device	Marking	$V_{(BR)R}$ Min (V)	$V_{(BR)R}$ @ I_R (μA)	C_T Max (pF)	C_T @ V_R (V)	R_S Max (ohms)	V_F Max (V)	V_F @ I_F (mA)	I_R Max (μA)	I_R @ V_R (V)	Pin Out Case Style
PIN DIODES (SINGLES)											
MMBV3700	4R	200	10	1	20	1			0.1	150	8
MMBV3401	4D	35	10	1	20	0.7			0.1	25	8
HOT CARRIER SCHOTTKY DIODES (SINGLES)											
MMBD101	4M	4	10	1	0		0.6	10	0.25	3	8
MMBD201	4S	20	10	1.5	15		0.6	10	0.2	15	8
MMBD301	4T	30	10	1.5	15		0.6	10	0.2	25	8
MMBD501	5F	50	10	1	20		1.2	10	0.2	25	8
MMBD701	5H	70	10	1	20		1.2	10	0.2	35	8
HOT CARRIER SCHOTTKY DIODES (DUALS)											
MMBD352	5G	4	10	1	0		0.60	10	0.25	3	11
MMBD353	4F	4	10	1	0		0.6	10	0.25	3	19

TABLE 16. Zener Diodes

Zener Diodes are offered in two popular series. The MMBZ5226 has the same specifications as the standard axial leaded 1N5226 series. The BCX84 series is identical to popular European series SOT-23's.

Pinout: 1-Anode, 2-NC, 3-Cathode (V_F = 0.9 V Max @ I_F = 10 mA for all types.)

Device	Marking	Test Current I_{ZT} mA	Zener Voltage V_Z (±5%) Nominal	Z_{ZK} I_Z = 0.25 mA Ω Max	Z_{ZT} $I_Z = I_{ZT}$ @ 10% Mod Ω Max	Max I_R μA	@ V_R V
MMBZ5226B	8A	20	3.3	1600	28	25	1.0
MMBZ5227B	8B	20	3.6	1700	24	15	1.0
MMBZ5228B	8C	20	3.9	1900	23	10	1.0
MMBZ5229B	8D	20	4.3	2000	22	5.0	1.0
MMBZ5230B	8E	20	4.7	1900	19	5.0	2.0
MMBZ5231B	8F	20	5.1	1600	17	5.0	2.0
MMBZ5232B	8G	20	5.6	1600	11	5.0	3.0
MMBZ5233B	8H	20	6.0	1600	7.0	5.0	3.5
MMBZ5234B	8J	20	6.2	1000	7.0	5.0	4.0
MMBZ5235B	8K	20	6.8	750	5.0	3.0	5.0
MMBZ5236B	8L	20	7.5	500	6.0	3.0	6.0
MMBZ5237B	8M	20	8.2	500	8.0	3.0	6.5
MMBZ5238B	8N	20	8.7	600	8.0	3.0	6.5
MMBZ5239B	8P	20	9.1	600	10	3.0	7.0
MMBZ5240B	8Q	20	10	600	17	3.0	8.0
MMBZ5241B	8R	20	11	600	22	2.0	8.4
MMBZ5242B	8S	20	12	600	30	1.0	9.1
MMBZ5243B	8T	9.5	13	600	13	0.5	9.9
MMBZ5244B	8U	9.0	14	600	15	0.1	10
MMBZ5245B	8V	8.5	15	600	16	0.1	11
MMBZ5246B	8W	7.8	16	600	17	0.1	12
MMBZ5247B	8X	7.4	17	600	19	0.1	13
MMBZ5248B	8Y	7.0	18	600	21	0.1	14
MMBZ5249B	8Z	6.6	19	600	23	0.1	14
MMBZ5250B	81A	6.2	20	600	25	0.1	15
MMBZ5251B	81B	5.6	22	600	29	0.1	17
MMBZ5252B	81C	5.2	24	600	33	0.1	18
MMBZ5253B	81D	5.0	25	600	35	0.1	19
MMBZ5254B	81E	4.6	27	600	41	0.1	21
MMBZ5255B	81F	4.5	28	600	44	0.1	21
MMBZ5256B	81G	4.2	30	600	49	0.1	23
MMBZ5257B	81H	3.8	33	700	58	0.1	25

TABLE 16. Zener Diodes (continued)

Pinout: 1-Anode, 2-NC, 3-Cathode

Device	Marking	V_{Z1} Volts Min	V_{Z1} Volts Max	V_{Z2} Volts Min	V_{Z2} Volts Max	V_{Z3} Volts Min	V_{Z3} Volts Max	@ I_Z mA I_{Z1}	I_{Z2}	I_{Z3}	Max I_R @ V_R (Volts)	I_R (μA)	Z_{ZT} (ohms) (max) @ $I_Z = I_{Z1}$
BZX84C3V3	Z14	3.1	3.5	2.3	2.9	3.6	4.2	5	1	20	1	5	95
BZX84C4V3	W9	4	4.6	3.3	4	4.4	5.1	5	1	20	1	3	90
BZX84C4V7	Z1	4.4	5	3.7	4.7	4.5	5.4	5	1	20	2	3	80
BZX84C5V1	Z2	4.8	5.4	4.2	5.3	5	5.9	5	1	20	2	2	60
BZX84C5V6	Z3	5.2	6	4.8	6	5.2	6.3	5	1	20	2	1	40
BZX84C6V2	Z4	5.8	6.6	5.6	6.6	5.8	6.8	5	1	20	4	3	10
BZX84C6V8	Z5	6.4	7.2	6.3	7.2	6.4	7.4	5	1	20	4	2	15
BZX84C7V5	Z6	7	7.9	6.9	7.9	7	8	5	1	20	5	1	15
BZX84C8V2	Z7	7.7	8.7	7.6	8.7	7.7	8	5	1	20	5	0.7	15
BZX84C9V1	Z8	8.5	9.6	8.4	9.6	8.5	9.7	5	1	20	6	0.5	15
BZX84C10	Z9	9.4	10.6	9.3	10.6	9.4	10.7	5	1	20	7	0.2	20
BZX84C11	Y1	10.4	11.6	10.2	11.6	10.4	11.8	5	1	20	8	0.1	20
BZX84C12	Y2	11.4	12.7	11.2	12.7	11.4	12.9	5	1	20	8	0.1	25
BZX84C13	Y3	12.4	14.1	12.3	14	12.5	14.2	5	1	20	8	0.1	30
BZX84C15	Y4	13.8	15.6	13.7	15.5	13.9	15.7	5	1	20	10.5	0.05	30
BZX84C16	Y5	15.3	17.1	15.2	17	15.4	17.2	5	1	20	11.2	0.05	40
BZX84C18	Y6	16.8	19.1	15.7	19	16.9	19.2	5	1	20	12.6	0.05	45
BZX84C20	Y7	18.8	21.2	18.7	21.1	18.9	21.4	5	1	20	14	0.05	55
BZX84C22	Y8	20.8	23.3	20.7	23.2	20.9	23.4	5	1	20	15.4	0.05	55
BZX84C24	Y9	22.8	25.6	22.7	25.5	22.9	25.7	5	1	20	16.8	0.05	70
BZX84C27	Y10	25.1	28.9	25	28.9	25.2	29.3	2	0.5	10	18.9	0.05	80(1)
BZX84C30	Y11	28	32	27.8	32	28.1	32.4	2	0.5	10	21	0.05	80(1)
BZX84C33	Y12	31	35	30.8	35	31.1	35.4	2	0.5	10	23.1	0.05	80(1)

NOTE: (1) rdiff @ I_Z = 2 mA

TABLE 17. Tuning Diodes

General Purpose, Abrupt and Hyper-Abrupt Junction, Voltage Variable Capacitance diodes are used for tuning and control of RF circuits through UHF frequencies.

Pinout: 1-Anode, 2-NC, 3-Cathode

Device	Marking	$V_{(BR)R}$ Min (V)	@ I_R (μA)	C_T Min (pF)	C_T Max (pF)	@ V_R (V)	Capacitance Ratio Min	Capacitance Ratio Max	Q Typ	@ V_R (V)	& f (MHz)	I_R Max (μA)	@ V_R (V)
TUNING DIODES													
MMBV105G	4E	30	10	1.8	2.8	25	4	6	350	3	50	0.05	28
MMBV109	4A	30	10	26	32	3	5	6.5	250	3	50	0.02	25
MMBV2101	4G	30	10	6.1	7.5	4	2.5	3.2	400	4	50	0.02	25
MMBV2103	4H	30	10	9	11	4	2.5	3.2	350	4	50	0.02	25
MMBV2108	4X	30	10	24.3	29.7	4	2.5	3.2	250	4	50	0.02	25
MMBV2109	4J	30	10	29.7	36.3	4	2.5	3.2	200	4	50	0.02	25
MMBV3102	4C	30	10	20	25	3	4.5	3.2	300	3	50	0.1	25
MMBV409		20		26	32	3	1.5	1.9	300	3	50	—	—
MMBV432L(1)	4B	14	10	43*	48.1*		1.5	2	100	2	50	0.1	9

(1) Monolithic Dual, Style 9 *Each Diodes

TABLE 18. Thyristors

SILICON CONTROLLED RECTIFIERS

Device	Marking	I_F (mA)	V_{FXM} (mA)	I_{GT} (μA)	V_{GT} (V)	I_H (mA)	Case Style
MMBS5060	5R	500	25	200	0.8	5	14
MMBS5061	5S	500	50	200	0.8	5	14
MMBS5062	5T	500	100	200	0.8	5	14

SILICON PROGRAMMABLE UNIJUNCTION TRANSISTORS

		I_P		I_{GAO}	I_V		
Device	Marking	R_G = 10 kΩ μA Min	R_G = 1 MΩ μA Max	@ 40 V nA Max	R_G = 10 kΩ μA Min	R_G = 1 MΩ μA Max	Case Style
MMBPU131	5Z	5	2	5	70	50	14
MMBP6027	5W	5	2	10	70	50	20
MMBP6028	5V	1	0.15	10	70	25	20

JAN, JANTX, JANTXV, and JANS

Motorola offers over 650 devices listed in QPL-19500, and is certified to supply small-signal bipolar devices to ALL FOUR quality levels of MIL-S-19500.

The following tables list the Motorola discrete devices and slash-sheet number as they appear on the Qualified Products List.

TABLE 1. Switching and High-Frequency Transistors (MIL-S-19500)

2N703 JAN	/153	2N2905 JAN,JTX,JTXV	/290	2N3506 JAN,JTX,JTXV	/349
2N706 JAN	/120	2N2905A JAN,JTX,JTXV	/290	2N3507 JAN,JTX,JTXV	/349
2N708 JAN,JTX	/312	2N2905AL JANS	/	2N3634 JAN,JTX,JTXV	/357
2N718A JAN,JTX,JTXV	/181	2N2906 JAN,JTX,JTXV	/291	2N3635 JAN,JTX,JTXV	/357
2N869A JAN,JTX	/283	2N2906A JAN,JTX,JTXV	/291	2N3636 JAN,JTX,JTXV	/357
2N914 JAN,JTX	/373	2N2907 JAN,JTX,JTXV	/291	2N3637 JAN,JTX,JTXV	/357
2N916 JAN	/271	2N2907A JAN,JTX,JTXV,JANS	/291	2N3700 JAN,JTX,JTXV	/391
2N918 JAN,JTX,JTXV,JANS	/301	2N2944A JAN,JTX,JTXV	/	2N3735 JAN,JTX,JTXV	/395
2N930 JAN,JTX	/253	2N2945A JAN,JTX,JTXV	/	2N3737 JAN,JTX,JTXV	/395
2N1132 JAN	/177	2N2946A JAN,JTX,JTXV	/	2N3743 JAN,JTX,JTXV	/397
2N1613 JAN,JTX,JTXV	/181	2N3013 JAN,JTX	/287	2N3762 JAN,JTX,JTXV	/396
2N2218 JAN,JTX,JTXV	/251	2N3019,S JAN,JTX,JTSV	/391	2N3763 JAN,JTX,JTXV	/396
2N2218A JAN,JTX,JTXV	/251	2N3250A JAN,JTX,JTXV	/323	2N3764 JAN,JTX,JTXV	/396
2N2219 JAN,JTX,JTXV	/251	2N3251A JAN,JTX,JTXV	/323	2N3765 JAN,JTX,JTXV	/396
2N2219A JAN,JTX,JTXV	/251	2N3253 JAN.	/347	2N4033 JAN,JTX,JTXV	/511
2N22219AL JANS	/	2N3444 JAN,JTX	/347	2N4261 JAN,JTX,JTXV	/511
2N2221 JAN,JTX,JTXV	/255	2N3467 JAN,JTX,JTXV	/348	2N4405 JAN,JTX,JTXV	/488
2N2221A JAN,JTX,JTXV	/255	2N3468 JAN,JTX,JTXV	/348	2N4449 JAN,JTX,JTXV	/317
2N2222 JAN,JTX,JTXV	/255	2N3485A JAN,JTX	/392	2N4453 JAN,JTX	/283
2N2222A JAN,JTX,JTXV,JANS	/225	2N3486A JAN,JTX	/392	2N4930 JAN,JTX,JTXV	/397
2N2369A JAN,JTX,JTXV,JANS	/317	2N3498 JAN,JTX,JTXV	/366	2N4931 JAN,JTX,JTXV	/397
2N2481 JAN,JTX	/268	2N3499 JAN,JTX,JTXV	/366	2N5581 JAN,JTX	/423
2N2904 JAN,JTX,JTXV	/290	2N3500 JAN,JTX,JTXV	/366	2N5582 JAN,JTX	/423
2N2904A JAN,JTX,JTXV	/	2N3501 JAN,JTX,JTXV	/366		

TABLE 2. Multiple Devices (MIL-S-19500)

2N2060 JAN,JTX,JTXV	/270	2N3811 JAN,JTX,JTXV	/336	2N5794 JAN,JTX,JTXV	/495
2N2919 JAN,JTX,JTXV	/355	2N4854 JAN,JTX,JTXV	/421	2N5795 JAN,JTX,JTXV	/496
2N2920 JAN,JTX,JTXV	/355	2N5793 JAN,JTX,JTXV	/495	2N5796 JAN,JTX,JTXV	/496
2N3810 JAN,JTX,JTXV	/336				

TABLE 3. Field-Effect Transistors (MIL-S-19500)

2N2608 JAN	/295	2N3823 JAN,JTX,JTXV	/375	2N4860 JAN,JTX,JTXV	/385
2N2609 JAN	/296	2N4856 JAN,JTX,JTXV	/385	2N4861 JAN,JTX,JTXV	/385
2N3330 JAN,JTX	/378	2N4857 JAN,JTX,JTXV	/385	2N4091 JAN,JTX,JTXV	/431
2N3821 JAN,JTX,JTXV	/375	2N4858 JAN,JTX,JTXV	/385	2N4092 JAN,JTX,JTXV	/431
2N3822 JAN,JTX,JTXV	/375	2N4859 JAN,JTX,JTXV	/385	2N4093 JAN,JTX,JTXV	/431

CECC

All CECC types are available to assessment levels E, F, L

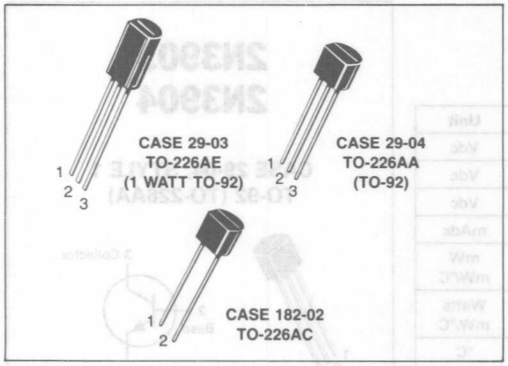
TABLE 4. Qualified Types

2N1613	2N2219	2N2222A	2N3019	2N2906	2N3439	2N5416
2N1711	2N2219A	2N2368	2N2904	2N2906A	2N3440	BC107-108-109
2N1893	2N2221	2N2369	2N2904A	2N2907	2N3501	CV9507
2N2218	2N2221A	2N2369A	2N2905	2N2907A	2N4033	PO7726
2N2218A	2N2222	2N2484	2N2905A	2N2894	2N5415	

Qualified products to CECC 50,000

Plastic-Encapsulated Devices

2



Motorola's plastic transistors and diodes encompass hundreds of devices spanning the gamut from general-purpose amplifiers and switches with a wide variety of characteristics to dedicated special-purpose devices for the most demanding applications. The popular high-volume TO-226AA (TO-92) package combines proven reliability, performance, economy and convenience to provide the perfect solution for industrial and consumer design problems.

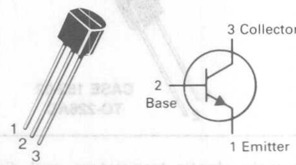
As an additional service to our customers Motorola will, upon request, supply the following:

- Radial tape and reel
- Axial tape and reel
- TO-205AA (TO-5) lead forming
- TO-206AA (TO-18) lead forming

Contact your Motorola representative for ordering information.

2N3903
2N3904

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltge	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
*Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

*THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

*Indicates Data in addition to JEDEC Requirements.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)		$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	6.0	—	Vdc
Base Cutoff Current ($V_{CE} = 30$ Vdc, $V_{EB} = 3.0$ Vdc)		I_{BL}	—	50	nAdc
Collector Cutoff Current ($V_{CE} = 30$ Vdc, $V_{EB} = 3.0$ Vdc)		I_{CEX}	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) ($I_C = 0.1$ mAdc, $V_{CE} = 1.0$ Vdc)	2N3903 2N3904	h_{FE}	20 40	— —	—
($I_C = 1.0$ mAdc, $V_{CE} = 1.0$ Vdc)	2N3903 2N3904		35 70	— —	
($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc)	2N3903 2N3904		50 100	150 300	
($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc)	2N3903 2N3904		30 60	— —	
($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc)	2N3903 2N3904		15 30	— —	
Collector-Emitter Saturation Voltage(1) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)		$V_{CE(sat)}$	— —	0.2 0.3	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)		$V_{BE(sat)}$	0.65 —	0.85 0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)	2N3903 2N3904	f_T	250 300	— —	MHz

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	4.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	8.0	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h_{ie}	1.0 1.0	8.0 10	k ohms
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h_{re}	0.1 0.5	5.0 8.0	X 10^{-4}
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h_{fe}	50 100	200 400	—
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{oe}	1.0	40	μmhos
Noise Figure (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 k ohms, f = 10 Hz to 15.7 kHz)	2N3903 2N3904	NF	— —	6.0 5.0	dB

SWITCHING CHARACTERISTICS

Characteristic	Conditions		Symbol	Min	Max	Unit
Delay Time	(V_{CC} = 3.0 Vdc, V_{BE} = 0.5 Vdc, I_C = 10 mAdc, I_{B1} = 1.0 mAdc)		t_d	—	35	ns
Rise Time			t_r	—	35	ns
Storage Time	(V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)	2N3903 2N3904	t_s	— —	175 200	ns
Fall Time			t_f	—	50	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 – DELAY AND RISE TIME EQUIVALENT TEST CIRCUIT

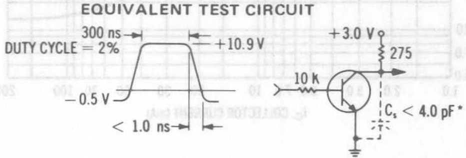
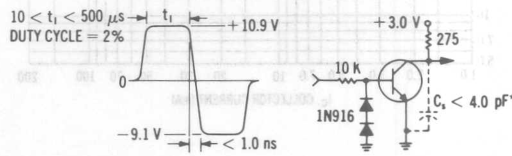


FIGURE 2 – STORAGE AND FALL TIME EQUIVALENT TEST CIRCUIT



*Total shunt capacitance of test jig and connectors

TYPICAL TRANSIENT CHARACTERISTICS

—— T_J = 25°C - - - T_J = 125°C

FIGURE 3 – CAPACITANCE

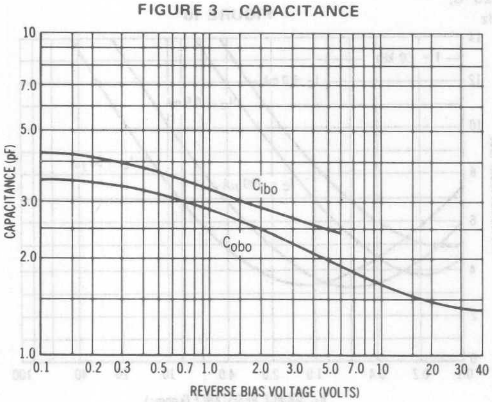


FIGURE 4 – CHARGE DATA

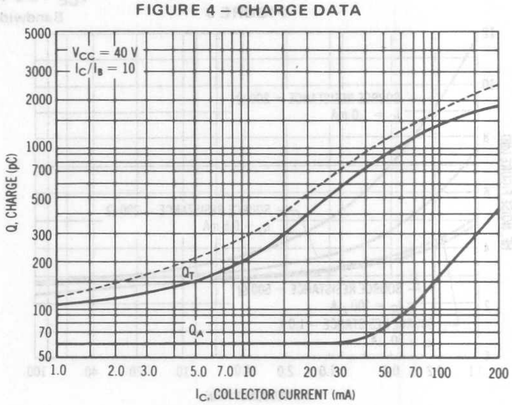


FIGURE 5 – TURN-ON TIME

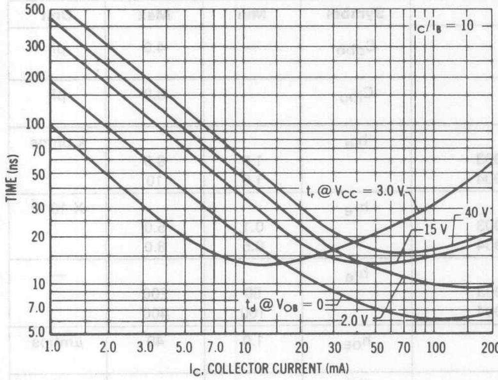


FIGURE 6 – RISE TIME

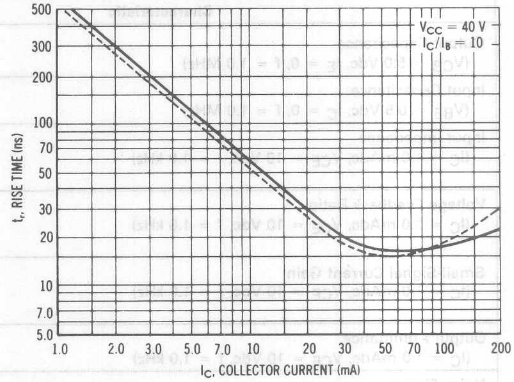


FIGURE 7 – STORAGE TIME

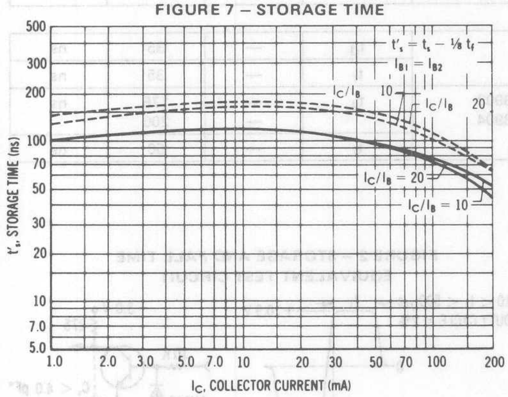
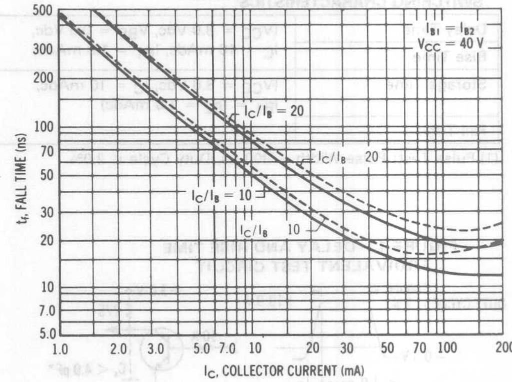


FIGURE 8 – FALL TIME



TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS

$V_{CE} = 5.0$ Vdc, $T_A = 25^{\circ}C$,
Bandwidth = 1.0 Hz

FIGURE 9

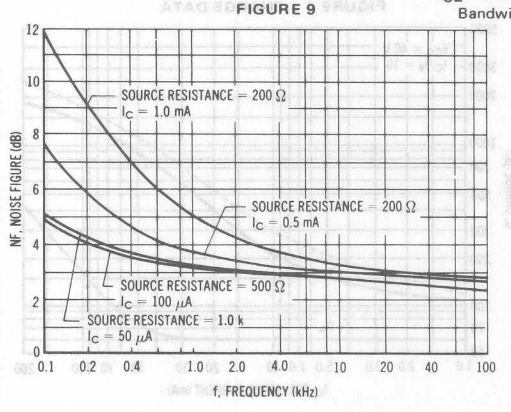


FIGURE 10

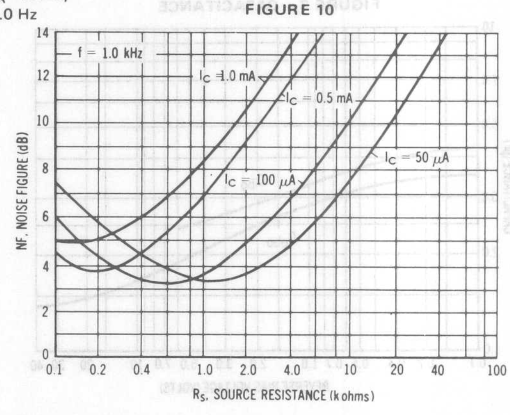


FIGURE 11 – CURRENT GAIN

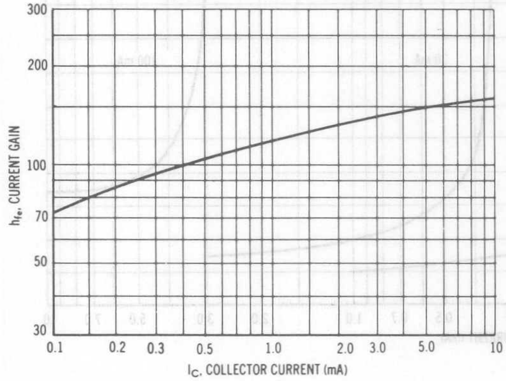


FIGURE 12 – OUTPUT ADMITTANCE

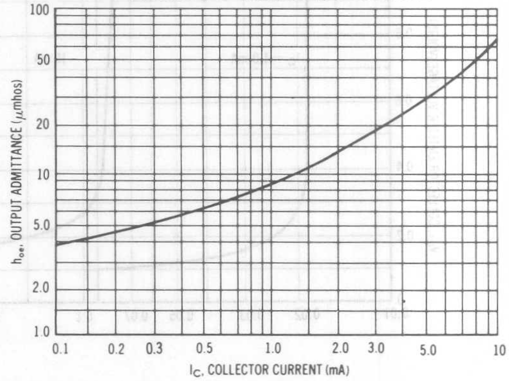


FIGURE 13 – INPUT IMPEDANCE

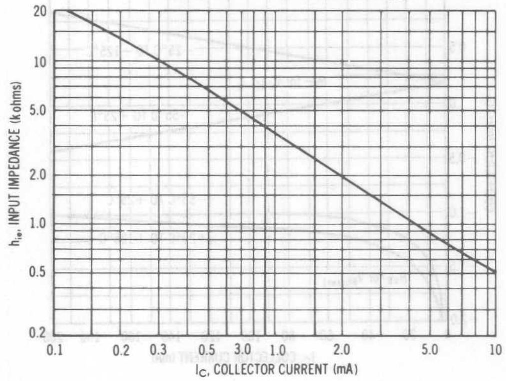
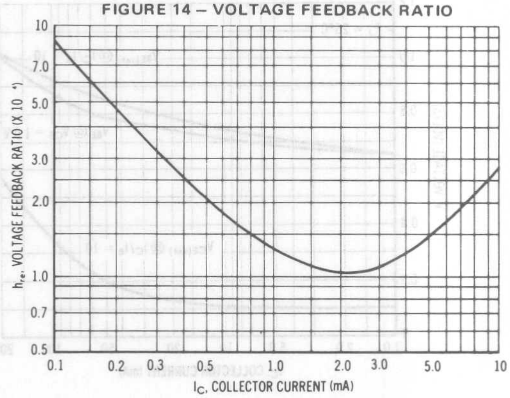
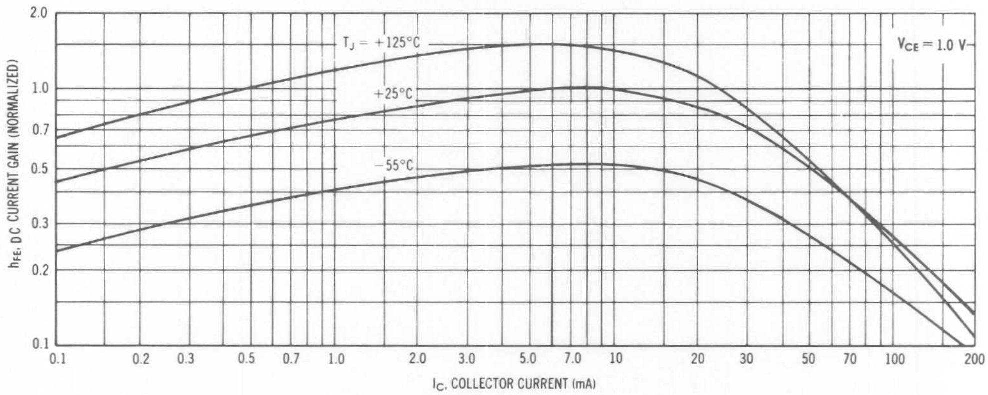


FIGURE 14 – VOLTAGE FEEDBACK RATIO



TYPICAL STATIC CHARACTERISTICS

FIGURE 15 – DC CURRENT GAIN



2

FIGURE 16 – COLLECTOR SATURATION REGION

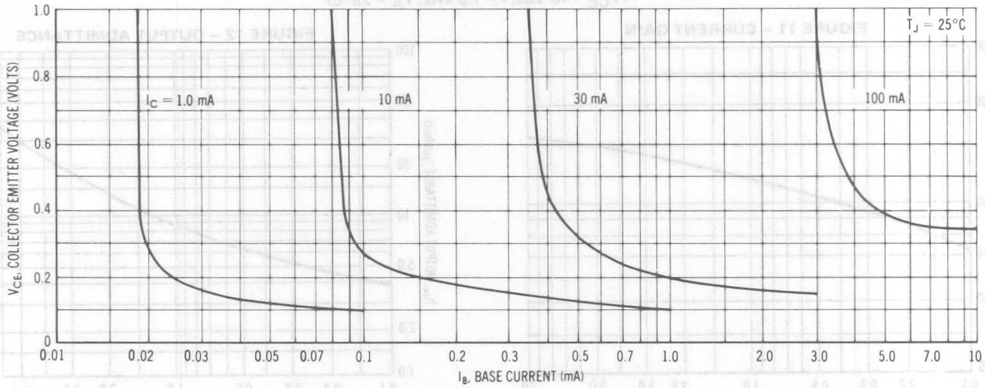


FIGURE 17 – "ON" VOLTAGES

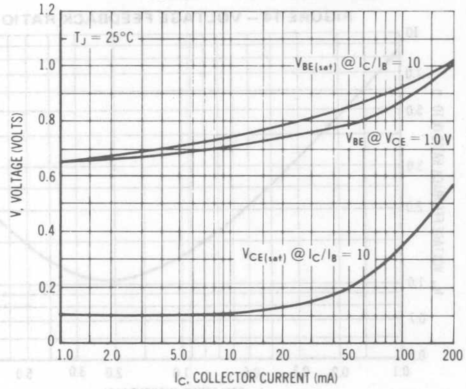
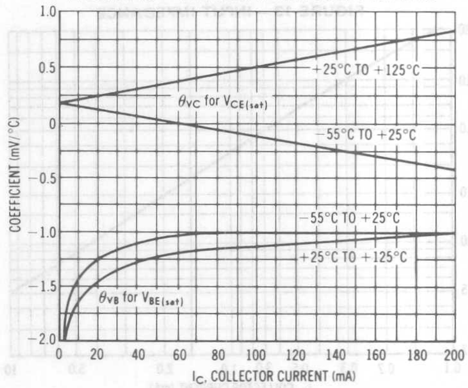


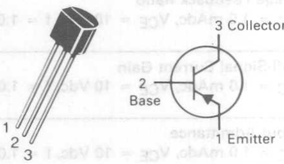
FIGURE 18 – TEMPERATURE COEFFICIENTS



2

2N3905
2N3906

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Power Dissipation @ T_A = 60°C	P_D	250	mW
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

*THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)		$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Base Cutoff Current (V_{CE} = 30 Vdc, V_{BE} = 3.0 Vdc)		I_{BL}	—	50	nAdc
Collector Cutoff Current (V_{CE} = 30 Vdc, V_{BE} = 3.0 Vdc)		I_{CEX}	—	50	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain		h_{FE}			—
(I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc)	2N3905 2N3906		30 60	— —	
(I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc)	2N3905 2N3906		40 80	— —	
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	2N3905 2N3906		50 100	150 300	
(I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	2N3905 2N3906		30 60	— —	
(I_C = 100 mAdc, V_{CE} = 1.0 Vdc)	2N3905 2N3906		15 30	— —	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{CE(sat)}$	— —	0.25 0.4	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{BE(sat)}$	0.65 —	0.85 0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	2N3905 2N3906	f_T	200 250	— —	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	4.5	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	10.0	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3905 2N3906	h_{ie}	0.5 2.0	8.0 12	k ohms
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3905 2N3906	h_{re}	0.1 0.1	5.0 10	$X\ 10^{-4}$
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3905 2N3906	h_{fe}	50 100	200 400	—
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3905 2N3906	h_{oe}	1.0 3.0	40 60	μmhos
Noise Figure (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 k ohm, f = 10 Hz to 15.7 kHz)	2N3905 2N3906	NF	— —	5.0 4.0	dB

SWITCHING CHARACTERISTICS

Characteristic	Conditions		Symbol	Min	Max	Unit
Delay Time	(V_{CC} = 3.0 Vdc, V_{BE} = 0.5 Vdc I_C = 10 mAdc, I_{B1} = 1.0 mAdc)		t_d	—	35	ns
Rise Time			t_r	—	35	ns
Storage Time	(V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)	2N3905 2N3906	t_s	— —	200 225	ns
Fall Time		2N3905 2N3906	t_f	— —	60 75	ns

(1) Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 – DELAY AND RISE TIME EQUIVALENT TEST CIRCUIT

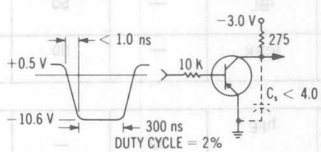
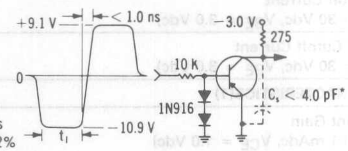


FIGURE 2 – STORAGE AND FALL TIME EQUIVALENT TEST CIRCUIT



*Total shunt capacitance of test jig and connectors

TRANSIENT CHARACTERISTICS

—— T_J = 25°C - - - T_J = 125°C

FIGURE 3 – CAPACITANCE

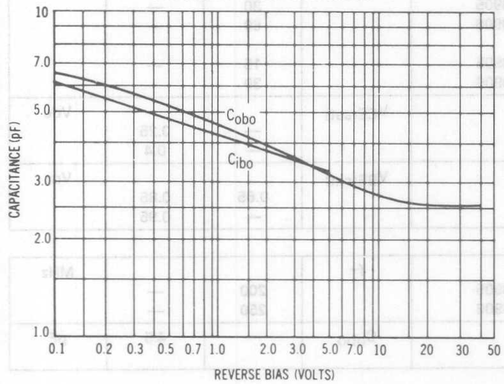


FIGURE 4 – CHARGE DATA

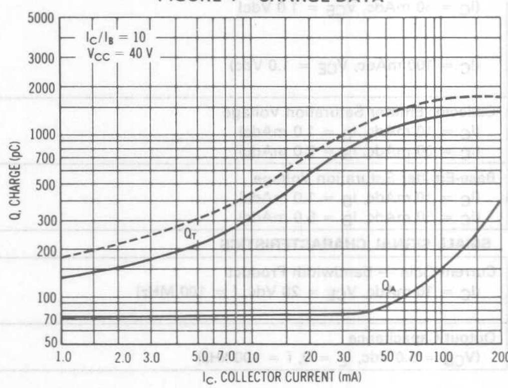


FIGURE 5 — TURN-ON TIME

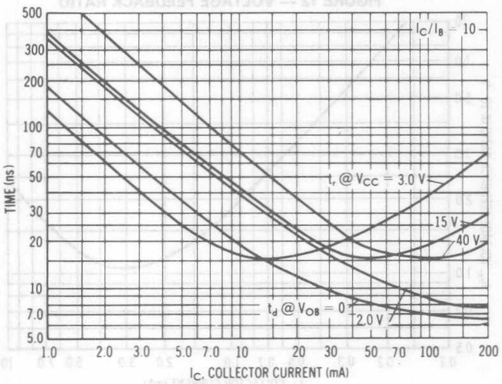
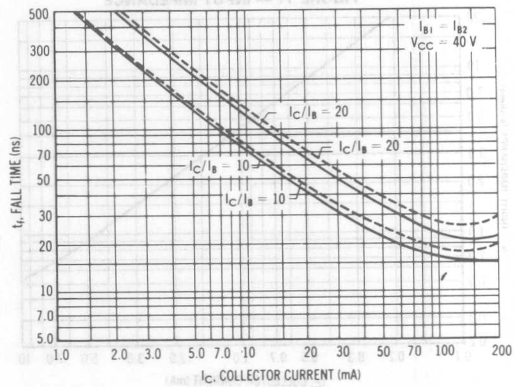


FIGURE 6 — FALL TIME



AUDIO SMALL SIGNAL CHARACTERISTICS

NOISE FIGURE VARIATIONS

V_{CE} = 5.0 Vdc, T_A = 25°C,
Bandwidth = 1.0 Hz

FIGURE 7 —

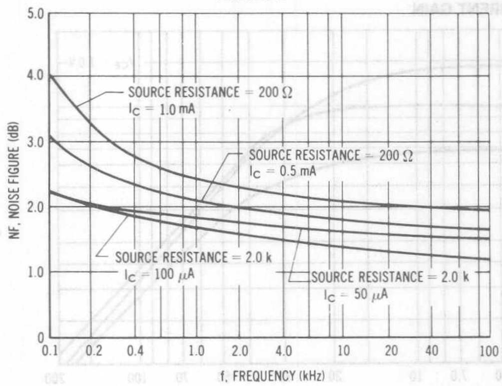
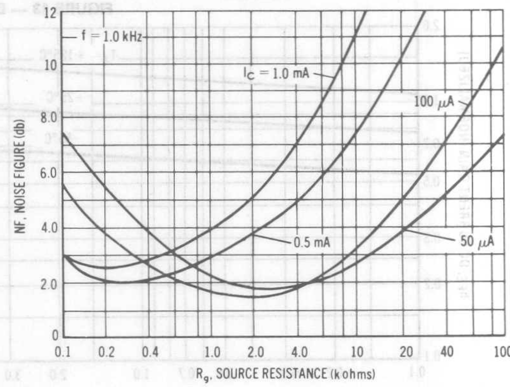


FIGURE 8 —



h PARAMETERS

(V_{CE} = 10 Vdc, f = 1.0 kHz, T_A = 25°C)

FIGURE 9 — CURRENT GAIN

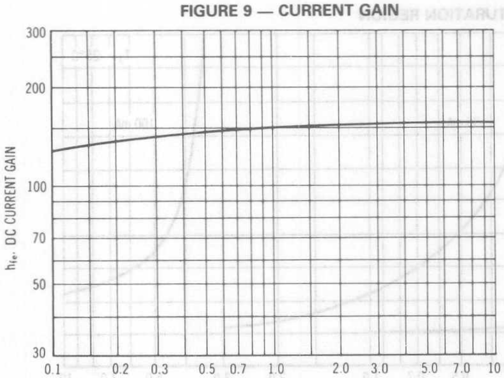
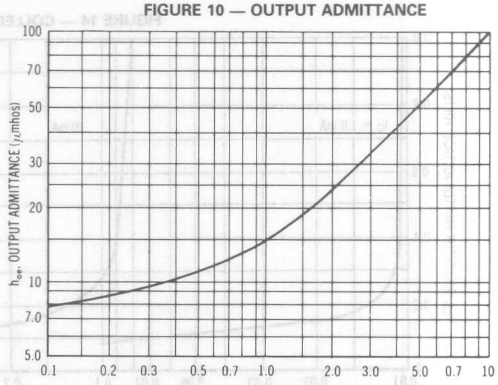


FIGURE 10 — OUTPUT ADMITTANCE



2

FIGURE 11 — INPUT IMPEDANCE

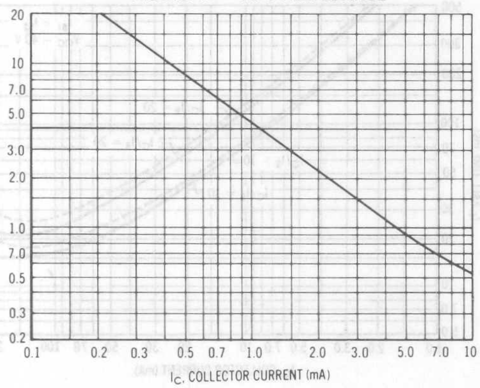
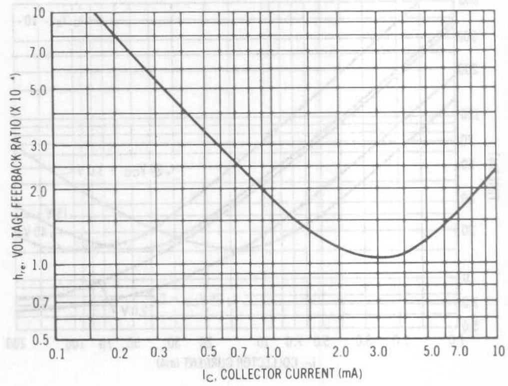


FIGURE 12 — VOLTAGE FEEDBACK RATIO



STATIC CHARACTERISTICS

FIGURE 13 — DC CURRENT GAIN

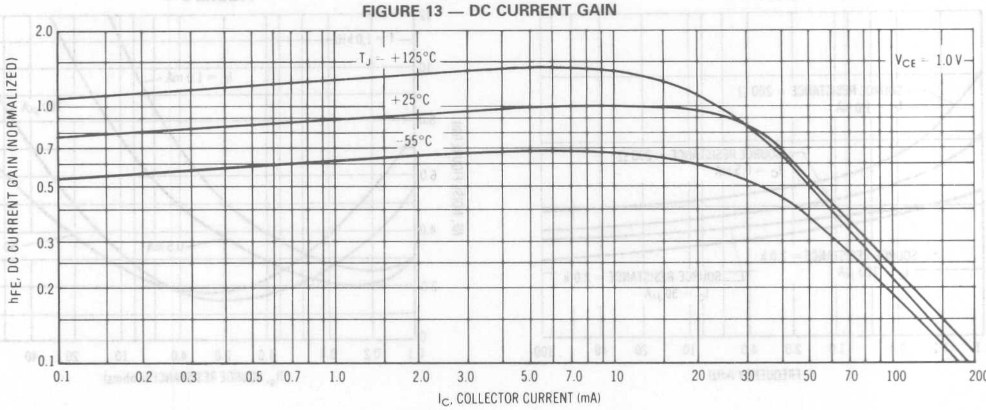


FIGURE 14 — COLLECTOR SATURATION REGION

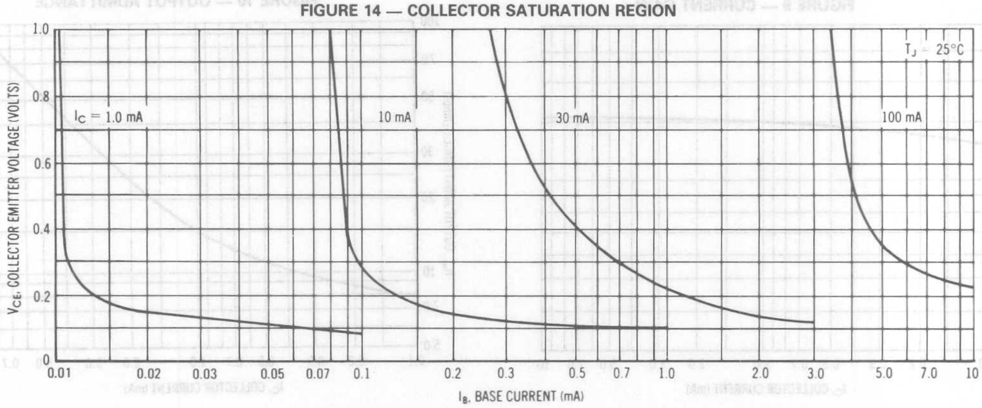


FIGURE 15 — "ON" VOLTAGES

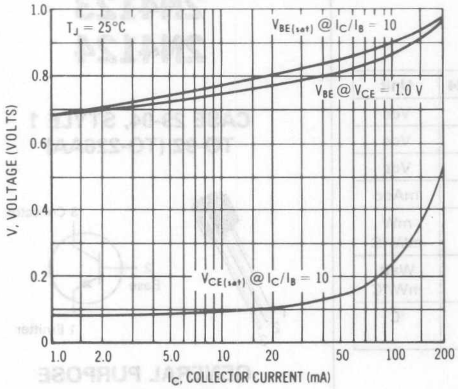
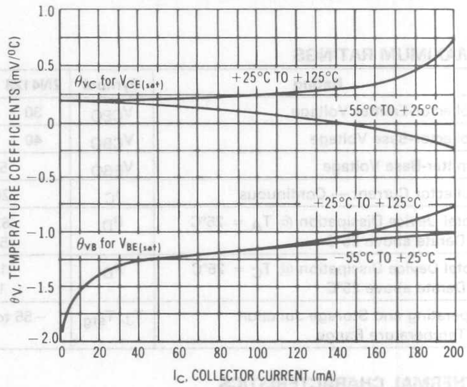
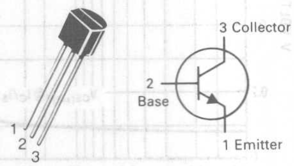


FIGURE 16 — TEMPERATURE COEFFICIENTS



2N4123
2N4124

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	2N4123	2N4124	Unit
Collector-Emitter Voltage	V_{CEO}	30	25	Vdc
Collector-Base Voltage	V_{CBO}	40	30	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_E = 0)	2N4123 2N4124	$V_{(BR)CEO}$	30 25	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	2N4123 2N4124	$V_{(BR)CBO}$	40 30	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0)		I_{CBO}	—	50	nAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)		I_{EBO}	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 2.0 mAdc, V_{CE} = 1.0 Vdc)	2N4123 2N4124	h_{FE}	50 120	150 360	—
(I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	2N4123 2N4124		25 60	— —	
Collector-Emitter Saturation Voltage(1) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{CE(sat)}$	—	0.3	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{BE(sat)}$	—	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	2N4123 2N4124	f_T	250 300	— —	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 MHz)		C_{obo}	—	4.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	8.0	pF
Collector-Base Capacitance (I_E = 0, V_{CB} = 5.0 V, f = 100 kHz)		C_{cb}	—	4.0	pF
Small-Signal Current Gain (I_C = 2.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N4123 2N4124	h_{fe}	50 120	200 480	—

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Current Gain — High Frequency (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	2N4123	$\vert h_{fe}\vert$	2.5	—	—
	2N4124		3.0	—	
(I_C = 2.0 mAdc, V_{CE} = 10 V, f = 1.0 kHz)	2N4123		50	200	
(I_C = 2.0 mAdc, V_{CE} = 10 V, f = 1.0 kHz)	2N4124		120	480	
Noise Figure (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 kohm, Noise Bandwidth = 10 Hz to 15.7 kHz)	2N4123	NF	—	6.0	dB
	2N4124		—	5.0	

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

FIGURE 1 — CAPACITANCE

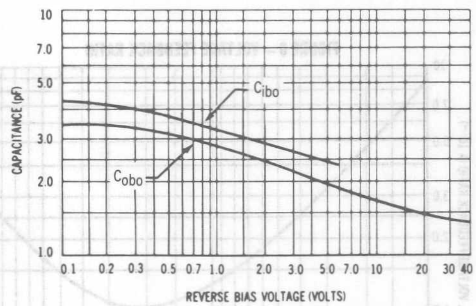
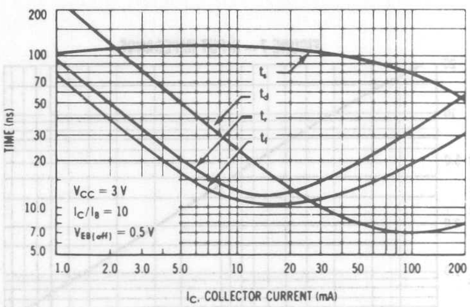


FIGURE 2 — SWITCHING TIMES



AUDIO SMALL SIGNAL CHARACTERISTICS

NOISE FIGURE

(V_{CE} = 5 Vdc, T_A = 25°C)
Bandwidth = 1.0 Hz

FIGURE 3 — FREQUENCY VARIATIONS

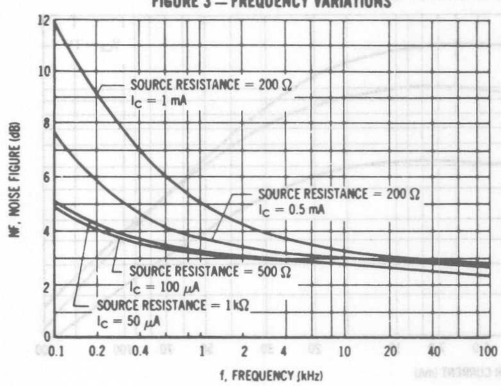
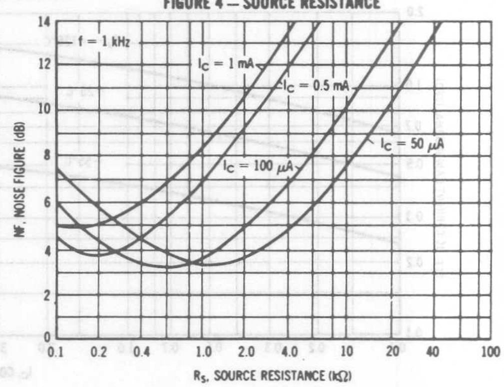


FIGURE 4 — SOURCE RESISTANCE



2

h PARAMETERS

V_{CE} = 10 V, f = 1 kHz, T_A = 25°C

FIGURE 5 — CURRENT GAIN

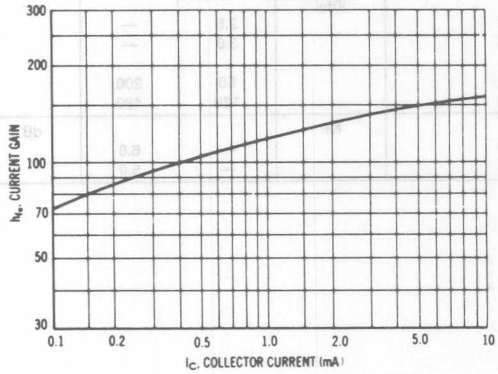


FIGURE 6 — OUTPUT ADMITTANCE

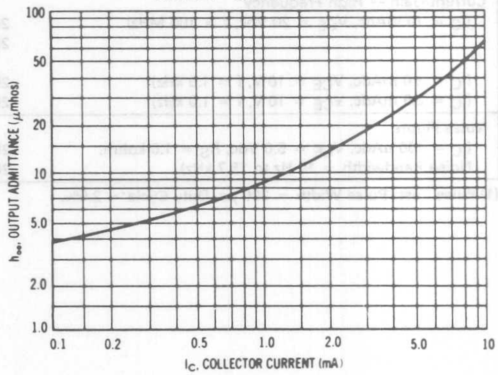


FIGURE 7 — INPUT IMPEDANCE

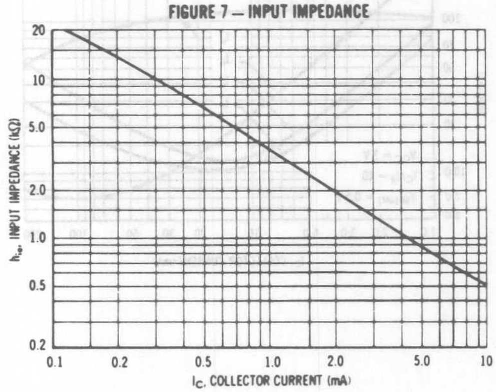
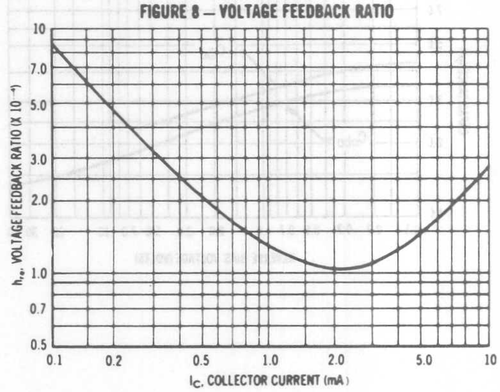


FIGURE 8 — VOLTAGE FEEDBACK RATIO



STATIC CHARACTERISTICS

FIGURE 9 — DC CURRENT GAIN

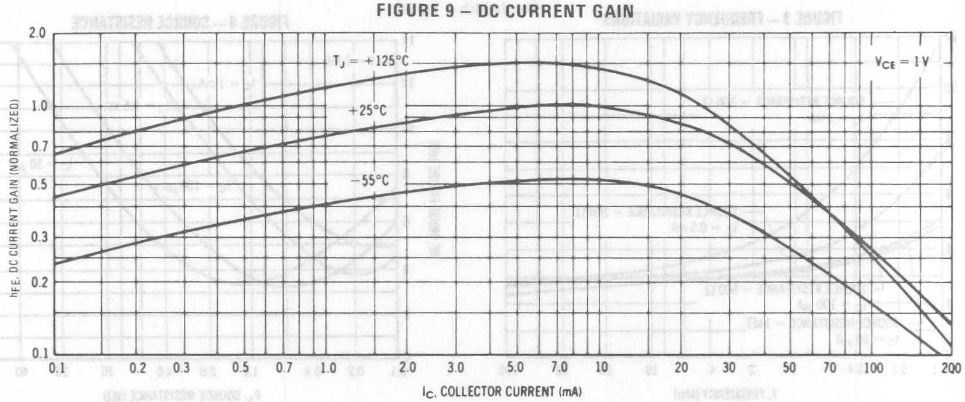


FIGURE 10 — COLLECTOR SATURATION REGION

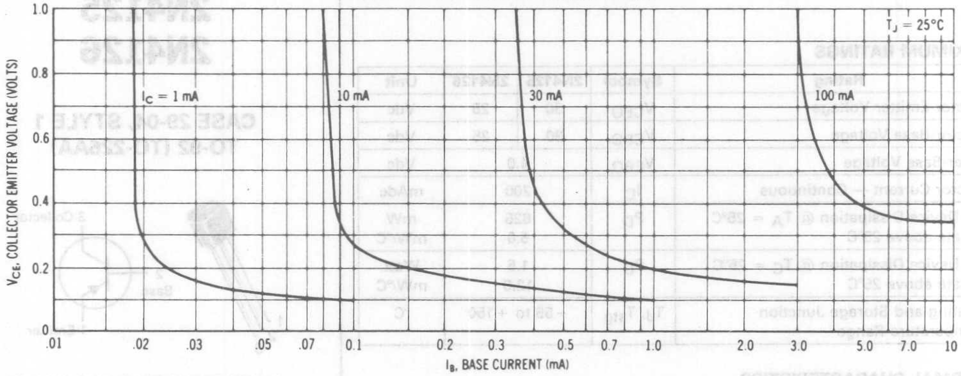


FIGURE 11 — "ON" VOLTAGES

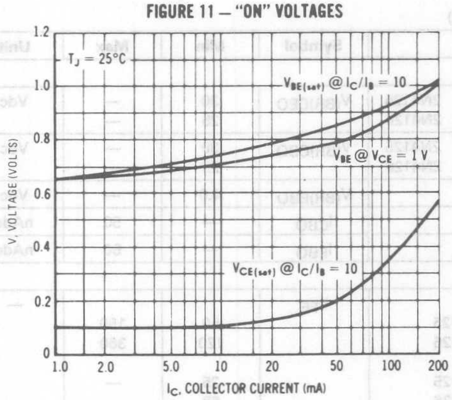
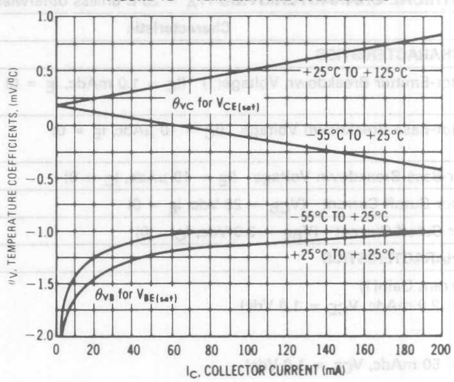
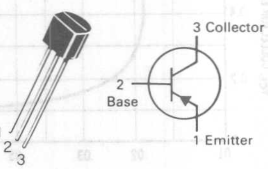


FIGURE 12 — TEMPERATURE COEFFICIENTS



2N4125
2N4126

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	2N4125	2N4126	Unit
Collector-Emitter Voltage	V_{CEO}	30	25	Vdc
Collector-Base Voltage	V_{CBO}	30	25	Vdc
Emitter-Base Voltage	V_{EBO}	4.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12.0		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

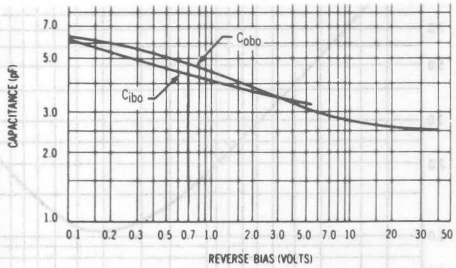
THERMAL CHARACTERISTICS

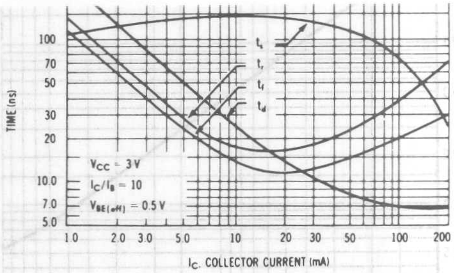
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_E = 0)	2N4125 2N4126	$V_{(BR)CEO}$	30 25	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	2N4125 2N4126	$V_{(BR)CBO}$	30 25	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0)		I_{CBO}	—	50	nAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)		I_{EBO}	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 2.0 mAdc, V_{CE} = 1.0 Vdc)	2N4125 2N4126	h_{FE}	50 120	150 360	—
(I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	2N4125 2N4126		25 60	— —	
Collector-Emitter Saturation Voltage(1) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{CE(sat)}$	—	0.4	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{BE(sat)}$	—	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	2N4125 2N4126	f_T	200 250	— —	MHz
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	10	pF
Collector-Base Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)		C_{cb}	—	4.5	pF
Small-Signal Current Gain (I_C = 2.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N4125 2N4126	h_{fe}	50 120	200 480	—
Current Gain — High Frequency (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	2N4125 2N4126	$\|h_{fe}\|$	2.0 2.5	— —	—
Noise Figure (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_G = 1.0 k ohm, Noise Bandwidth = 10 Hz to 15.7 kHz)	2N4125 2N4126	NF	— —	5.0 4.0	dB

(1) Pulse Test: Pulse Width ≤ 300 μsec, Duty Cycle = 2.0%.





AUDIO SMALL SIGNAL CHARACTERISTICS

NOISE FIGURE

V_{CE} = 5.0 Vdc, T_A = 25°C,
Bandwidth = 1.0 Hz

FIGURE 3 — FREQUENCY VARIATIONS

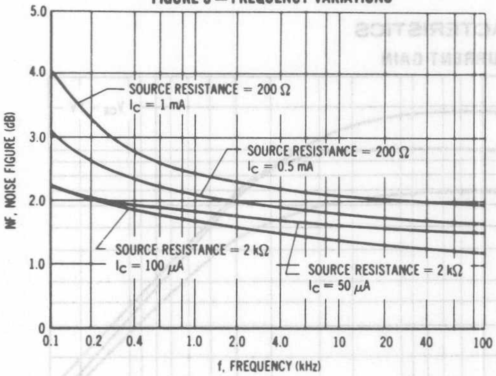
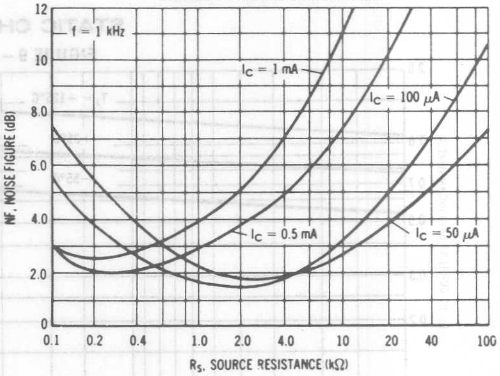


FIGURE 4 — SOURCE RESISTANCE



h PARAMETERS

V_{CE} = 10 V, f = 1 kHz, T_A = 25°C

FIGURE 5 — CURRENT GAIN

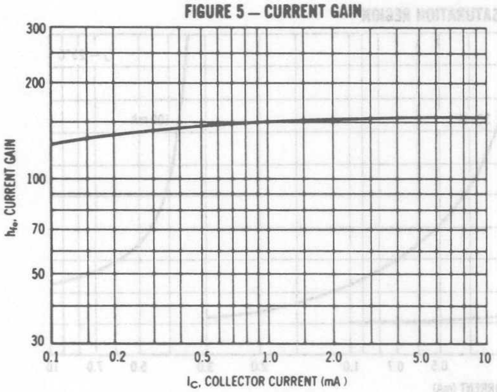
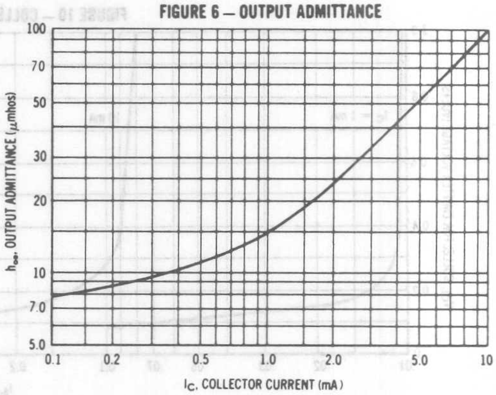


FIGURE 6 — OUTPUT ADMITTANCE



2

FIGURE 7 — INPUT IMPEDANCE

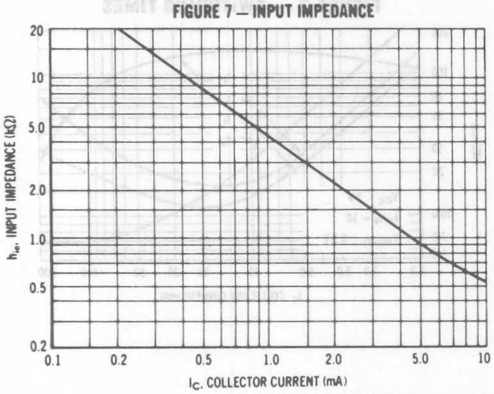
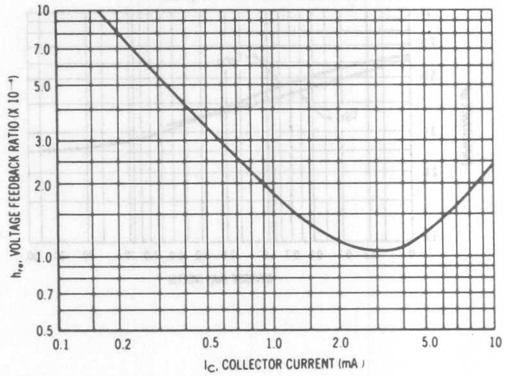


FIGURE 8 — VOLTAGE FEEDBACK RATIO



STATIC CHARACTERISTICS

FIGURE 9 — DC CURRENT GAIN

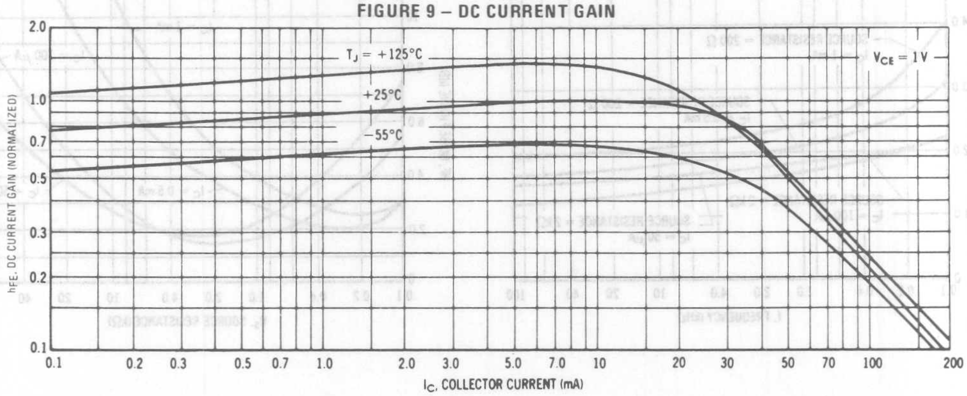


FIGURE 10 — COLLECTOR SATURATION REGION

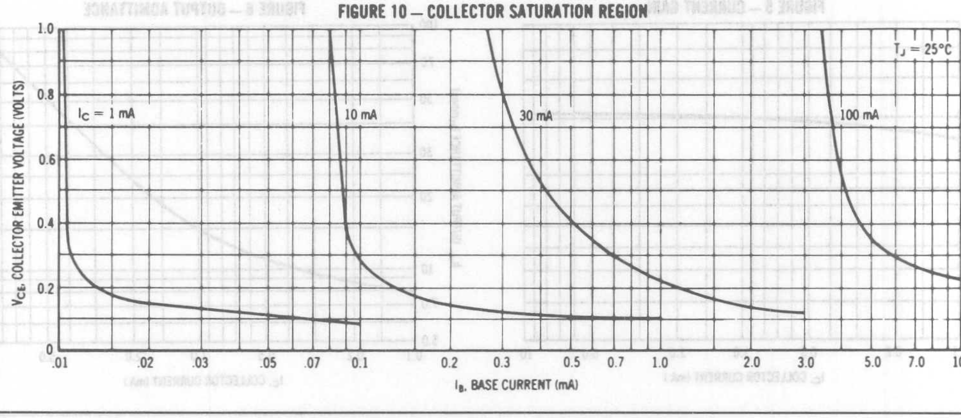


FIGURE 11 — "ON" VOLTAGES

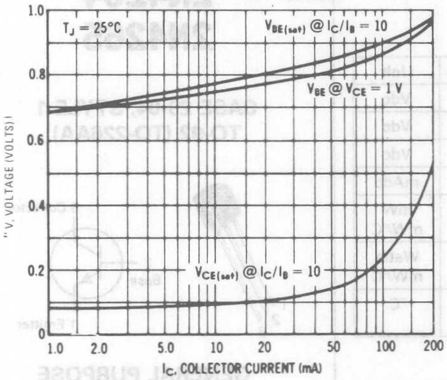
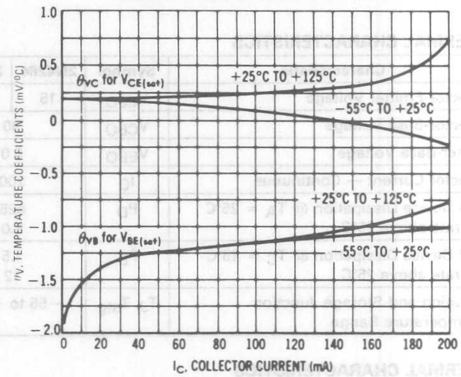


FIGURE 12 — TEMPERATURE COEFFICIENTS



THERMAL CHARACTERISTICS

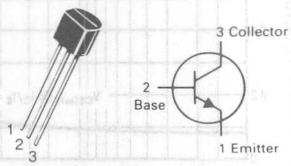
Characteristic	Symbol	2N4264	2N4265	Unit
Collector-Emitter Voltage	V_{CEO}	15	12	Vdc
Collector-Base Voltage	V_{CBO}	30		Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

2N4265

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



GENERAL PURPOSE TRANSISTORS

NPN SILICON

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

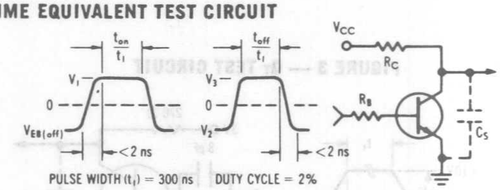
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_E = 0)	2N4264 2N4265	$V_{(BR)CEO}$	15 12	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	20	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	6.0	—	Vdc
Base Cutoff Current (V_{CE} = 12 Vdc, $V_{EB(off)}$ = 0.25 Vdc) (V_{CE} = 12 Vdc, $V_{EB(off)}$ = 0.25 Vdc, T_A = 100°C)		I_{BEV}	— —	0.1 10	μAdc
Collector Cutoff Current (V_{CE} = 12 Vdc, $V_{EB(off)}$ = 0.25 Vdc)		I_{CEX}	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc)	2N4264 2N4265	h_{FE}	25 30	— —	—
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	2N4264 2N4265		40 100	160 400	
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc, T_A = −55°C)	2N4264 2N4265		20 45	— —	
(I_C = 30 mAdc, V_{CE} = 1.0 Vdc)	2N4264 2N4265		40 90	— —	
(I_C = 100 mAdc, V_{CE} = 1.0 Vdc)(1)	2N4264 2N4265		30 55	— —	
(I_C = 200 mAdc, V_{CE} = 1.0 Vdc)(1)	2N4264 2N4265		20 35	— —	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc)(1)		$V_{CE(sat)}$	— —	0.22 0.35	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc)(1)		$V_{BE(sat)}$	0.65 0.75	0.80 0.95	Vdc

Characteristic		Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	350	—	MHz
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	8.0	pF
Collector-Base Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)		C_{cb}	—	4.0	pF
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 10 Vdc, $V_{EB(off)}$ = 2.0 Vdc, I_C = 100 mAdc, I_{B1} = 10 mAdc) (Fig. 1, Test Condition C)	t_d	—	8.0	ns
Rise Time		t_r	—	15	ns
Storage Time	V_{CC} = 10 Vdc, (I_C = 10 mAdc, for t_s) (I_C = 100 mA for t_f) I_{B1} = I_{B2} = 10 mAdc) (Fig. 1, Test Condition C)	t_s	—	20	ns
Fall Time		t_f	—	15	ns
Turn-On Time	(V_{CC} = 3.0 Vdc, $V_{EB(off)}$ = 1.5 Vdc, I_C = 10 mAdc, I_{B1} = 3.0 mAdc) (Fig. 1, Test Condition A)	t_{on}	—	25	ns
Turn-Off Time	(V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = 3.0 mAdc, I_{B2} = 1.5 mAdc) (Fig. 1, Test Condition A)	t_{off}	—	35	ns
Storage Time	(V_{CC} = 10 Vdc, I_C = 10 mA I_{B1} = I_{B2} = 10 mAdc) (Fig. 1, Test Condition A)	t_s	—	20	ns
Total Control Charge	(V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_B = mAdc) (Fig. 1, Test Condition B)	Q_T	—	80	pC

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

FIGURE 1 — SWITCHING TIME EQUIVALENT TEST CIRCUIT

TEST CONDITION	I_C	V_{CC}	R_B	R_C	$C_{S(max)}$	$V_{EB(off)}$	V_1	V_2	V_3
	mA	V	Ω	Ω	pF	V	V	V	V
A	10	3	3300	270	4	−1.5	10.55	−4.15	10.70
B	10	10	560	960	4	–	–	−4.65	6.55
C	100	10	560	96	12	−2.0	6.35	−4.65	6.55



CURRENT GAIN CHARACTERISTICS

FIGURE 2 — MINIMUM CURRENT GAIN

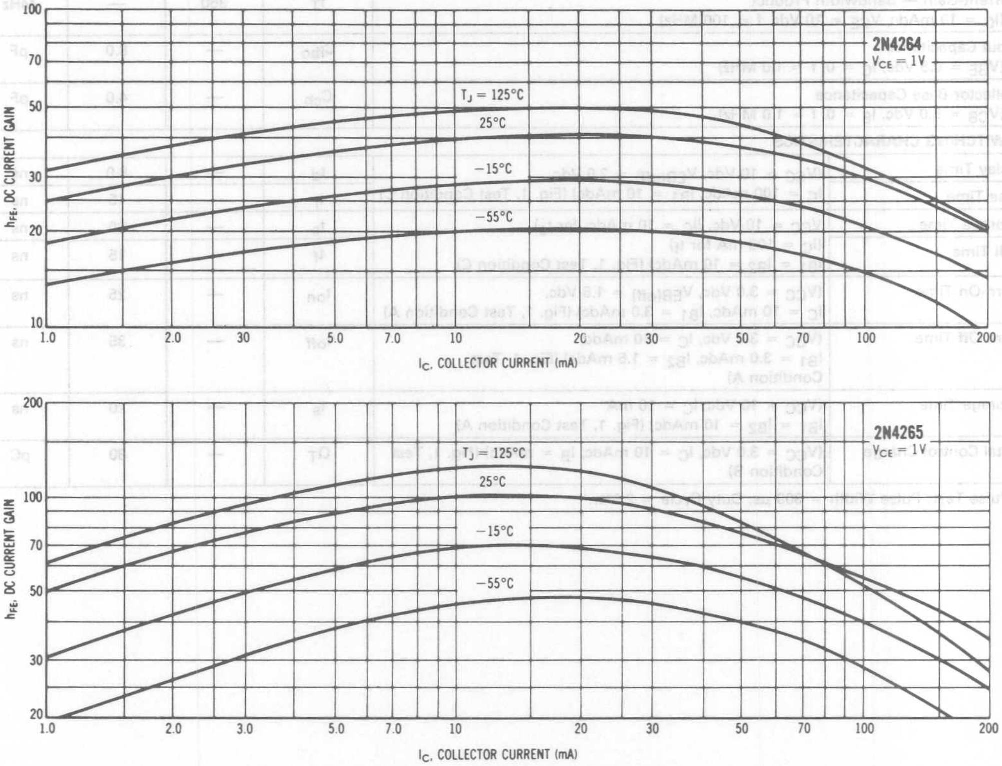


FIGURE 3 — Q_T TEST CIRCUIT

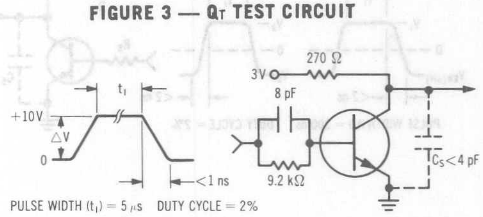
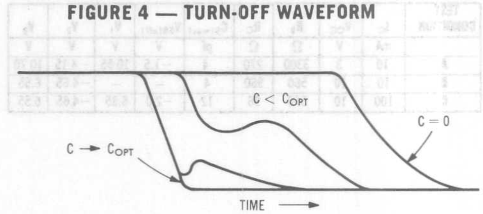


FIGURE 4 — TURN-OFF WAVEFORM



NOTE 1

When a transistor is held in a conductive state by a base current, I_B, a charge, Q_S, is developed or "stored" in the transistor. Q_S may be written: $Q_S = Q_1 + Q_V + Q_X$.

Q_1 is the charge required to develop the required collector current. This charge is primarily a function of alpha cutoff frequency. Q_V is the charge required to charge the collector-base feedback capacity. Q_X is excess charge resulting from overdrive, i.e., operation in saturation.

The charge required to turn a transistor "on" to the edge of saturation is the sum of Q_1 and Q_V which is defined as the active region charge, Q_A. $Q_A = I_{B1}t_r$ when the transistor is driven by a constant current step (I_{B1}) and $I_{B1} << \frac{I_C}{h_{FE}}$.

If I_B were suddenly removed, the transistor would continue to conduct until Q_S is removed from the active regions through an external path or through internal recombination. Since the internal recombination time is long compared to the ultimate capability of a transistor, a charge, Q_T, of opposite polarity, equal in magnitude, can be stored on an external capacitor, C, to neutralize the internal charge and considerably reduce the turn-off time of the transistor. Figure 3 shows the test circuit and Figure 4 the turn-off waveform. Given Q_T from Figure 13, the external C for worst-case turn-off in any circuit is: $C = Q_T/\triangle V$, where $\triangle V$ is defined in Figure 3.

"ON" CONDITION CHARACTERISTICS

FIGURE 5 — COLLECTOR SATURATION REGION

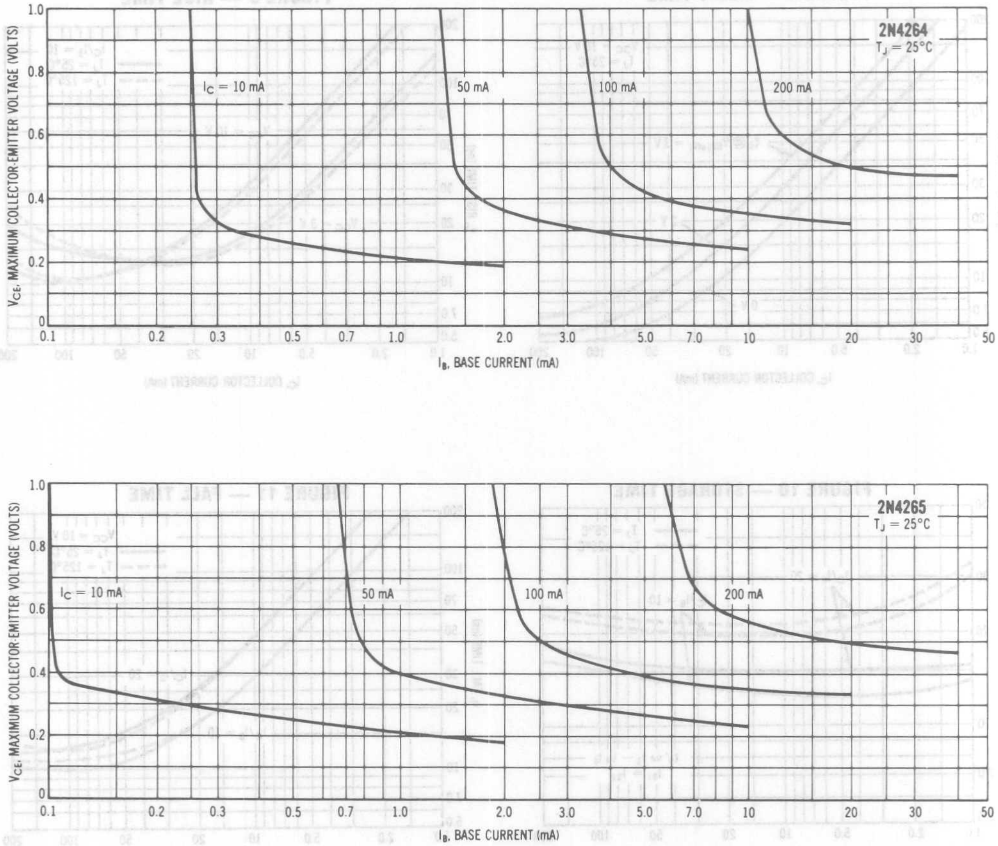


FIGURE 6 — SATURATION VOLTAGE LIMITS

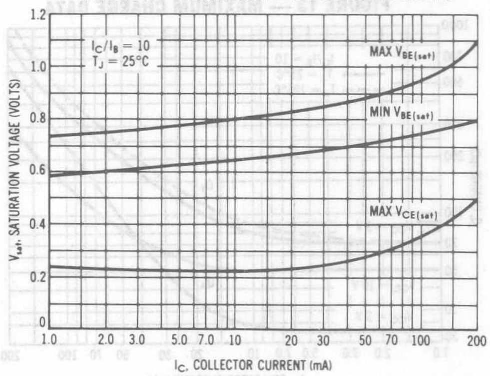
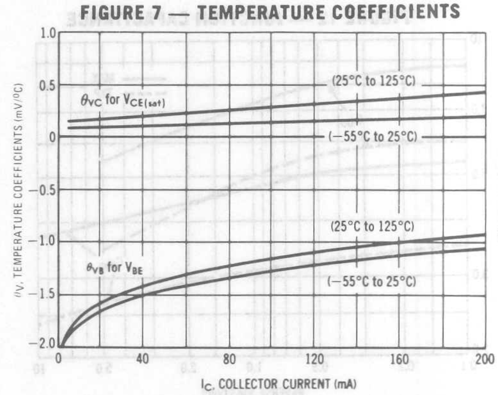


FIGURE 7 — TEMPERATURE COEFFICIENTS



2

DYNAMIC CHARACTERISTICS

FIGURE 8 — DELAY TIME

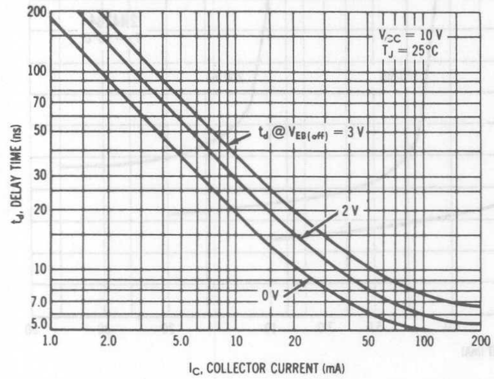


FIGURE 9 — RISE TIME

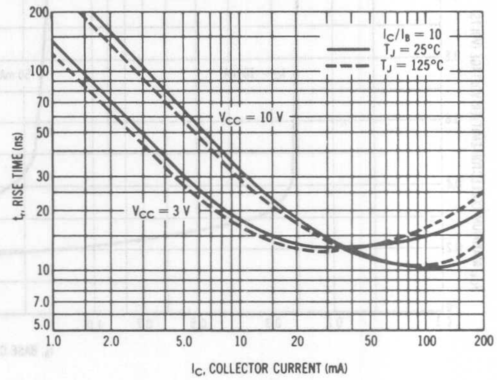


FIGURE 10 — STORAGE TIME

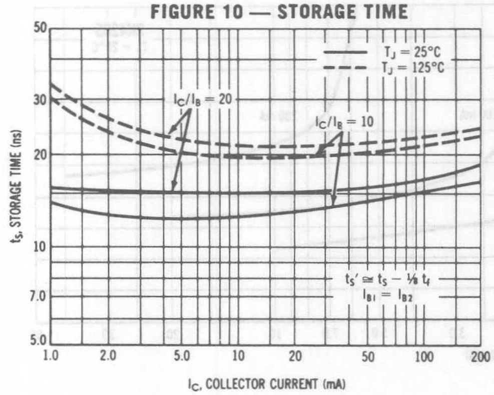


FIGURE 11 — FALL TIME

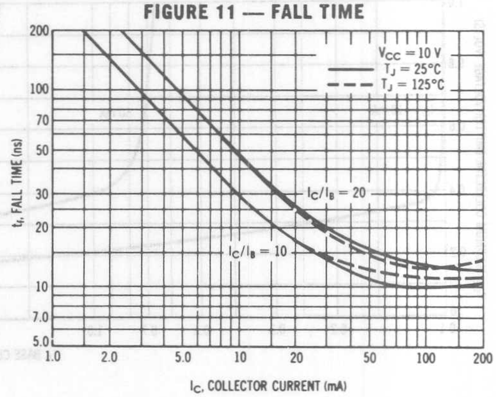


FIGURE 12 — JUNCTION CAPACITANCE

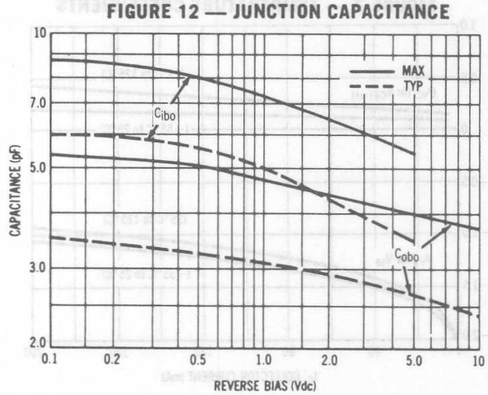
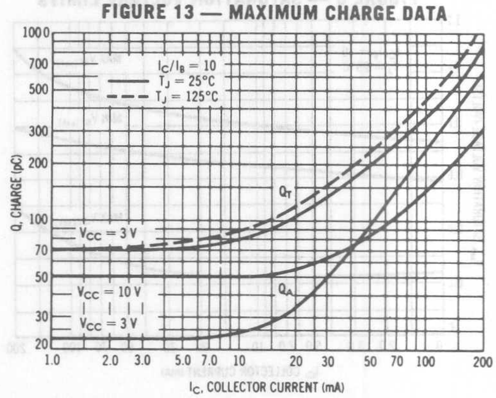
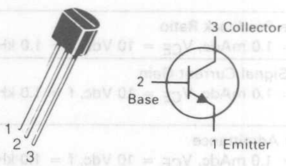


FIGURE 13 — MAXIMUM CHARGE DATA



CASE 29-04, STYLE 1
TO-92 (TO-226AA)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	600	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.1$ mAdc, $I_E = 0$)		$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 0.1$ mAdc, $I_C = 0$)		$V_{(BR)EBO}$	6.0	—	Vdc
Base Cutoff Current ($V_{CE} = 35$ Vdc, $V_{EB} = 0.4$ Vdc)		I_{BEV}	—	0.1	μAdc
Collector Cutoff Current ($V_{CE} = 35$ Vdc, $V_{EB} = 0.4$ Vdc)		I_{CEX}	—	0.1	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain		h_{FE}			—
($I_C = 0.1$ mAdc, $V_{CE} = 1.0$ Vdc)	2N4401		20	—	
($I_C = 1.0$ mAdc, $V_{CE} = 1.0$ Vdc)	2N4400 2N4401		20 40	— —	
($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc)	2N4400 2N4401		40 80	— —	
($I_C = 150$ mAdc, $V_{CE} = 1.0$ Vdc)	2N4400 2N4401		50 100	150 300	
($I_C = 500$ mAdc, $V_{CE} = 2.0$ Vdc)	2N4400 2N4401		20 40	— —	
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)		$V_{CE(sat)}$	 — —	 0.4 0.75	Vdc
Base-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)		$V_{BE(sat)}$	 0.75 —	 0.95 1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 20$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	2N4400 2N4401	f_T	200 250	— —	MHz
Collector-Base Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 100 kHz)		C_{cb}	—	6.5	pF

2

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Emitter-Base Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{eb}	—	30	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N4400 2N4401	h_{ie}	0.5 1.0	7.5 15	k ohms
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{re}	0.1	8.0	$\times 10^{-4}$
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N4400 2N4401	h_{fe}	20 40	250 500	—
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{oe}	1.0	30	μmhos

SWITCHING CHARACTERISTICS

		Symbol	Min	Max	Unit
Delay Time	(V_{CC} = 30 Vdc, V_{EB} = 2.0 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_d	—	15	ns
Rise Time		t_r	—	20	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_s		225	ns
Fall Time		t_f	—	30	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

FIGURE 1 — TURN-ON TIME

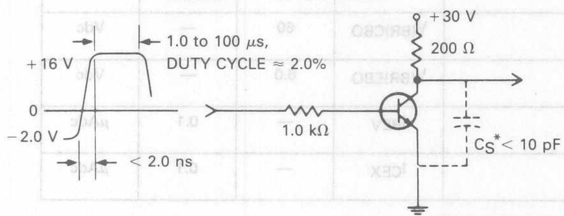
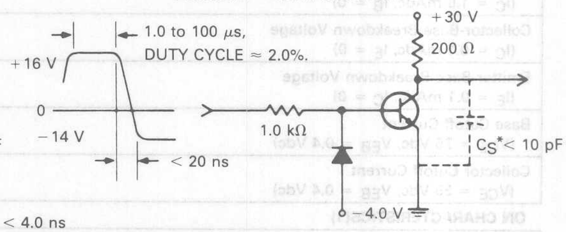


FIGURE 2 — TURN-OFF TIME



Scope rise time < 4.0 ns
*Total shunt capacitance of test jig connectors, and oscilloscope

TRANSIENT CHARACTERISTICS

——— 25°C - - - - 100°C

FIGURE 3 — CAPACITANCES

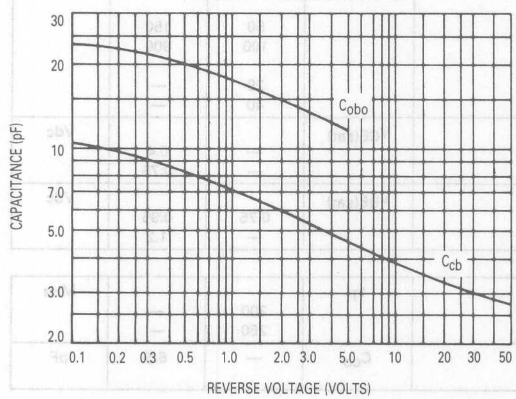


FIGURE 4 — CHARGE DATA

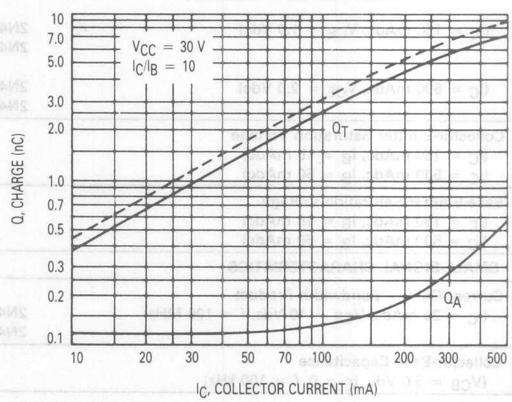


FIGURE 5 — TURN-ON TIME

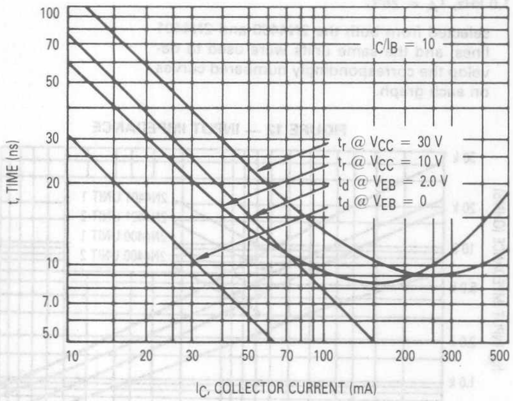


FIGURE 6 — RISE AND FALL TIMES

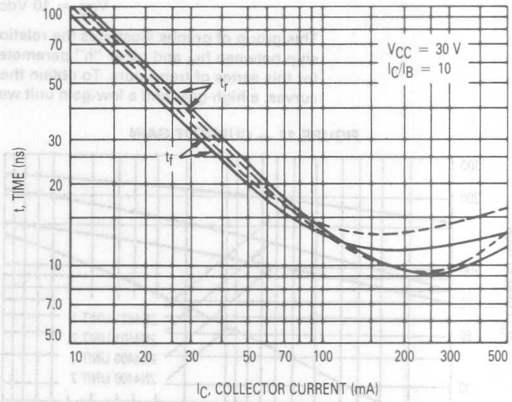


FIGURE 7 — STORAGE TIME

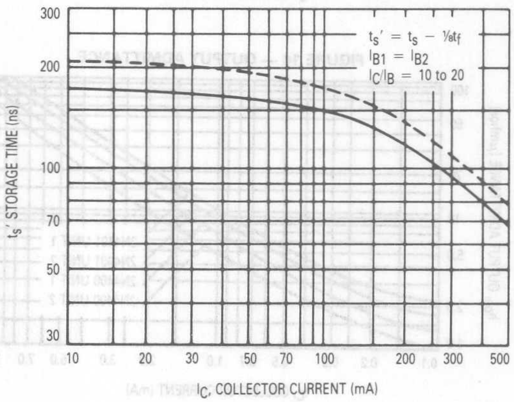
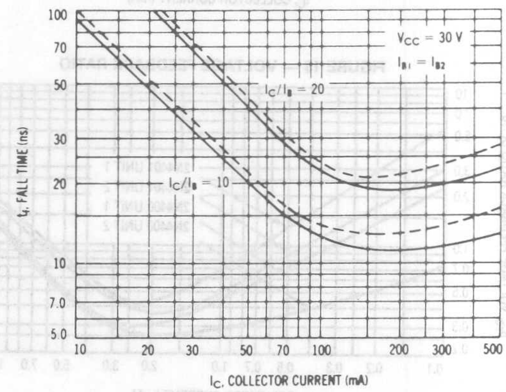


FIGURE 8 — FALL TIME



SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE

V_{CE} = 10 Vdc, T_A = 25°C

Bandwidth = 1.0 Hz

FIGURE 9 — FREQUENCY EFFECTS

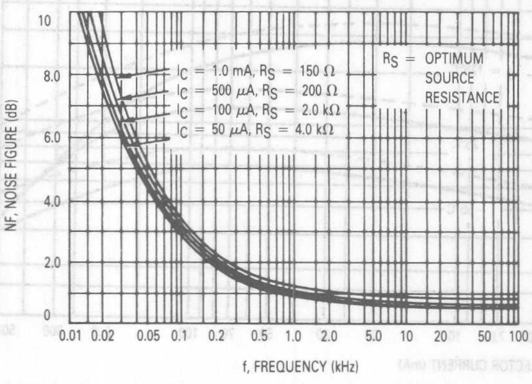
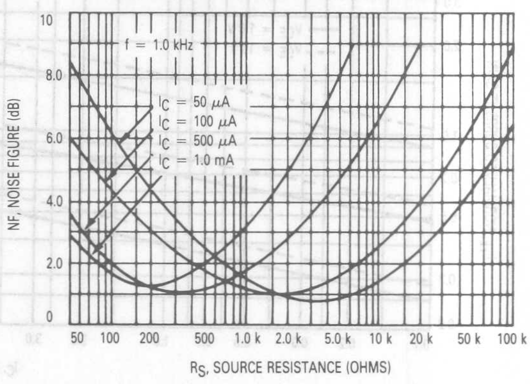


FIGURE 10 — SOURCE RESISTANCE EFFECTS



2

h PARAMETERS

$V_{CE} = 10$ Vdc, f = 1.0 kHz, $T_A = 25°C$

This group of graphs illustrates the relationship between h_{fe} and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were selected from both the 2N4400 and 2N4401 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

FIGURE 11 — CURRENT GAIN

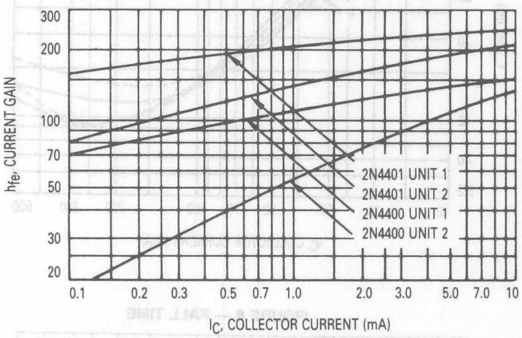


FIGURE 12 — INPUT IMPEDANCE

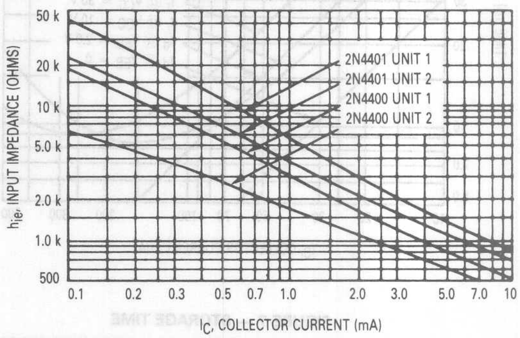


FIGURE 13 — VOLTAGE FEEDBACK RATIO

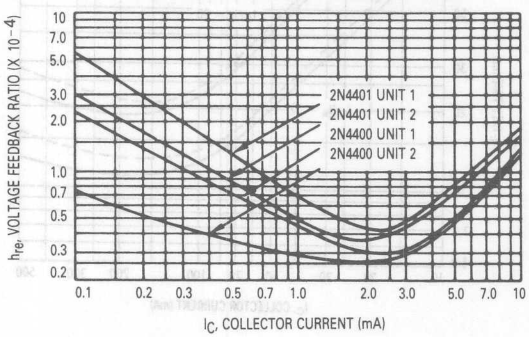
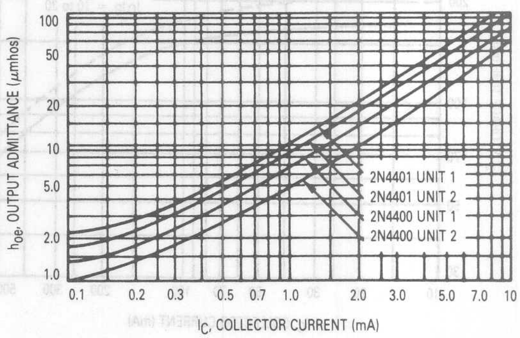


FIGURE 14 — OUTPUT ADMITTANCE



STATIC CHARACTERISTICS

FIGURE 15 — DC CURRENT GAIN

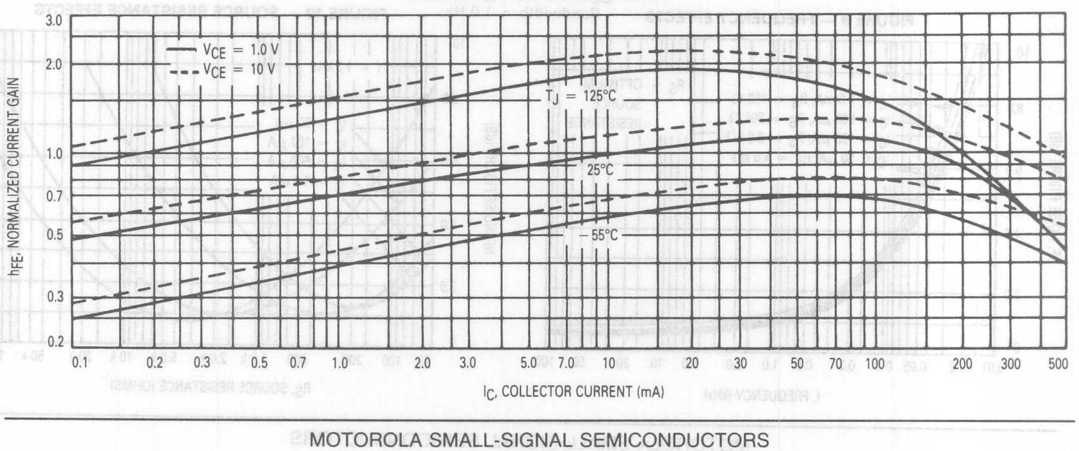


FIGURE 16 — COLLECTOR SATURATION REGION

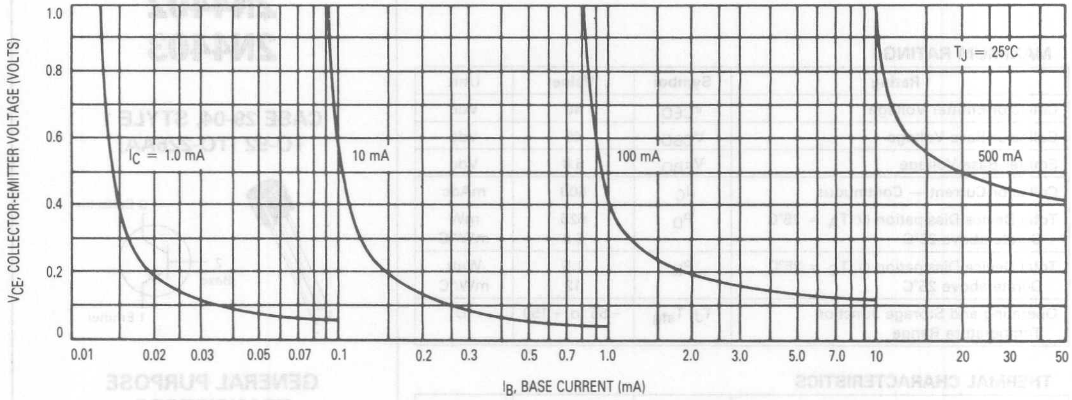


FIGURE 17 — "ON" VOLTAGES

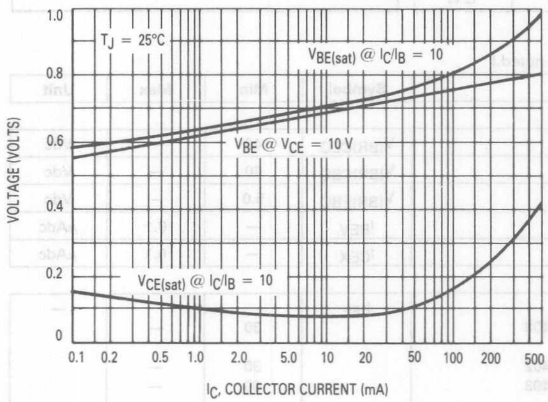
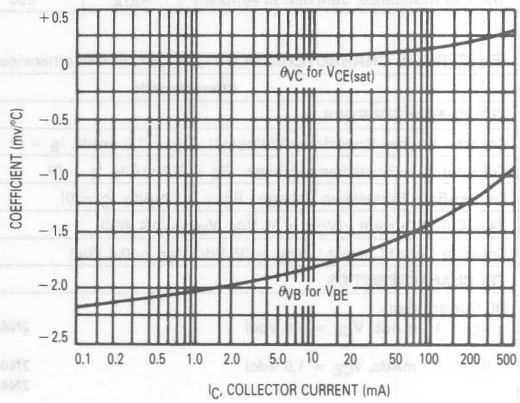
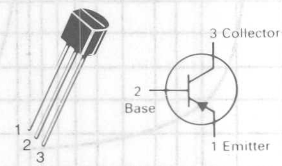


FIGURE 18 — TEMPERATURE COEFFICIENTS



2N4402
2N4403

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



GENERAL PURPOSE TRANSISTORS

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	600	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.1$ mAdc, $I_E = 0$)		$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 0.1$ mAdc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Base Cutoff Current ($V_{CE} = 35$ Vdc, $V_{BE} = 0.4$ Vdc)		I_{BEV}	—	0.1	μAdc
Collector Cutoff Current ($V_{CE} = 35$ Vdc, $V_{BE} = 0.4$ Vdc)		I_{CEX}	—	0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 1.0$ Vdc)	2N4403	h_{FE}	30	—	—
($I_C = 1.0$ mAdc, $V_{CE} = 1.0$ Vdc)	2N4402 2N4403		30 60	— —	
($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc)	2N4402 2N4403		50 100	— —	
($I_C = 150$ mAdc, $V_{CE} = 2.0$ Vdc)(1)	2N4402 2N4403		50 100	150 300	
($I_C = 500$ mAdc, $V_{CE} = 2.0$ Vdc)(1)	Both		20	—	
Collector-Emitter Saturation Voltage(1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)		$V_{CE(sat)}$	 — —	 0.4 0.75	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)		$V_{BE(sat)}$	 0.75 —	 0.95 1.3	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 20$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	2N4402 2N4403	f_T	150 200	— —	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 140 kHz)		C_{cb}	—	8.5	pF
Emitter-Base Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 140 kHz)		C_{eb}	—	30	pF
Input Impedance ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	2N4402 2N4403	h_{ie}	750 1.5k	7.5k 15k	ohms

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{re}	0.1	8.0	X 10^{-4}
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N4402	h_{fe}	30	250	—
	2N4403		60	500	
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{oe}	1.0	100	µmhos
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 30 Vdc, V_{BE} = 2.0 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_d	—	15	ns
Rise Time		t_r	—	20	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_s	—	225	ns
Fall Time		t_f	—	30	ns

(1) Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUIT

FIGURE 1 — TURN-ON TIME

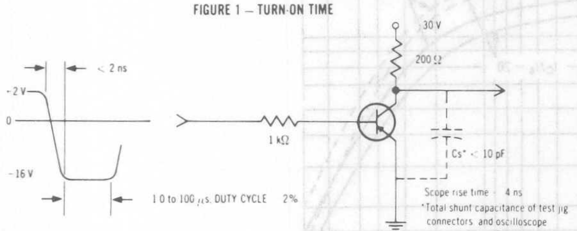
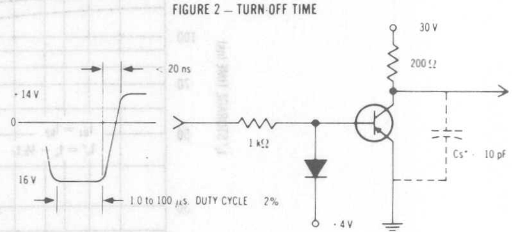


FIGURE 2 — TURN-OFF TIME



TRANSIENT CHARACTERISTICS

—— 25°C — — — 100°C

FIGURE 3 — CAPACITANCES

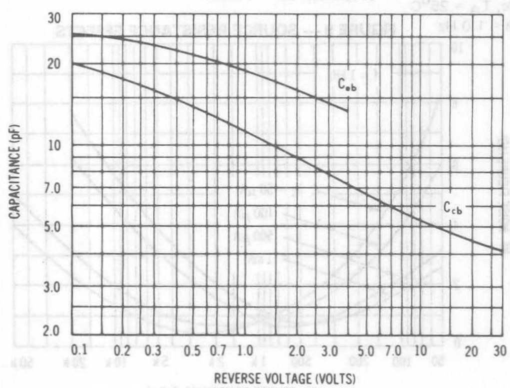
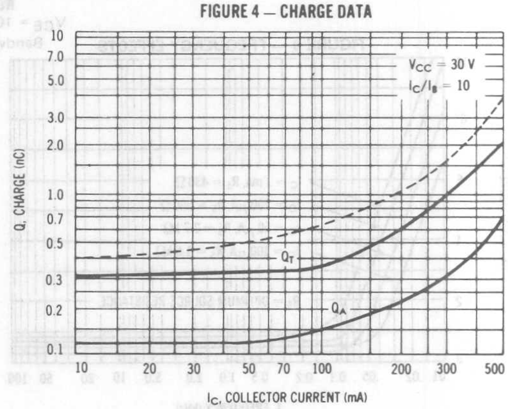


FIGURE 4 — CHARGE DATA



2

FIGURE 5 — TURN-ON TIME

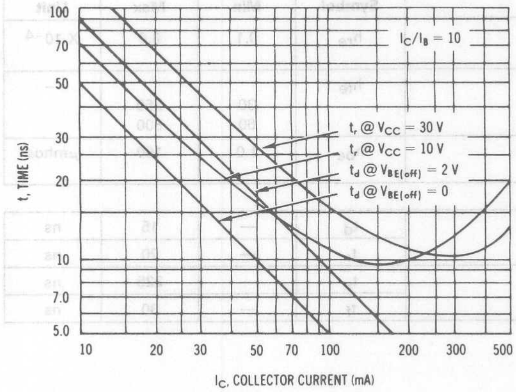


FIGURE 6 — RISE TIME

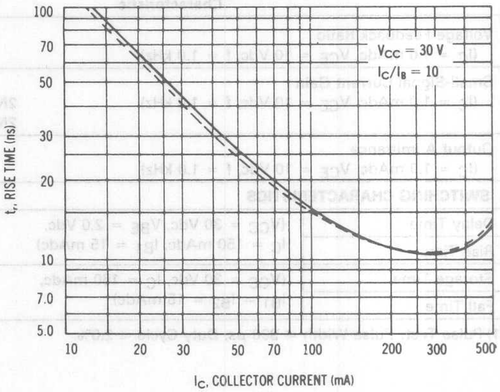
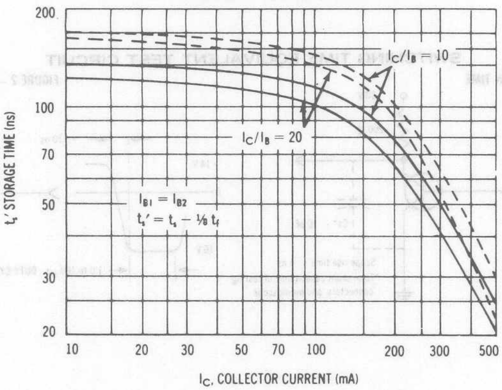


FIGURE 7 — STORAGE TIME



SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE

V_{CE} = 10 Vdc, T_A = 25°C

Bandwidth = 1.0 Hz

FIGURE 8 — FREQUENCY EFFECTS

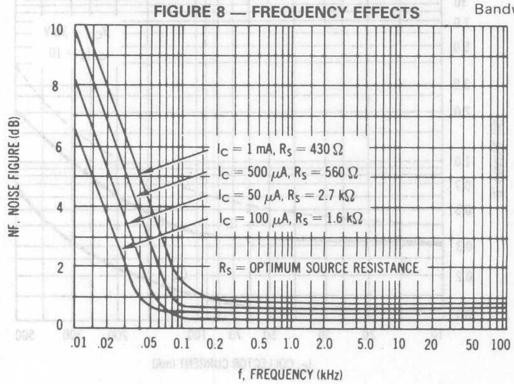
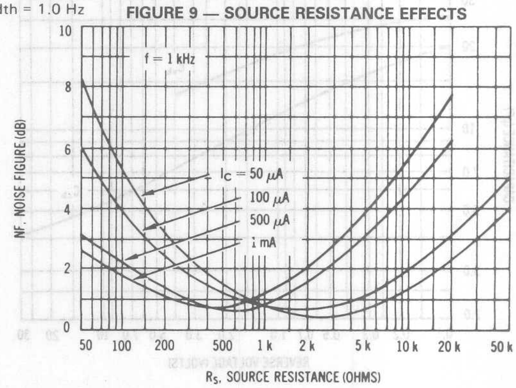


FIGURE 9 — SOURCE RESISTANCE EFFECTS



h PARAMETERS

V_{CE} = 10 Vdc, f = 1 kHz, T_A = 25°C

This group of graphs illustrates the relationship between h_{fe} and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were selected from both the 2N4402 and 2N4403 lines, and the same units were used to develop the correspondingly-numbered curves on each graph.

FIGURE 10 — CURRENT GAIN

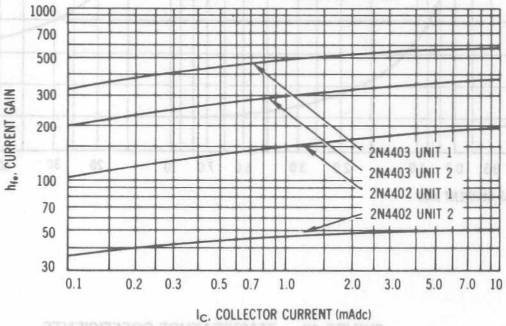


FIGURE 11 — INPUT IMPEDANCE

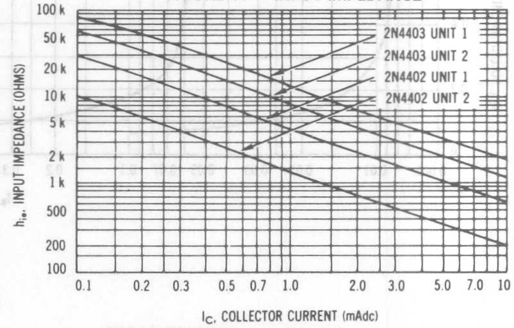


FIGURE 12 — VOLTAGE FEEDBACK RATIO

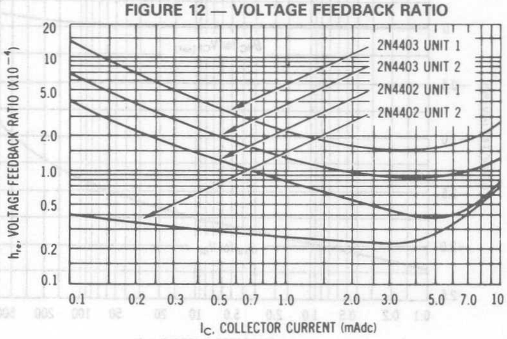
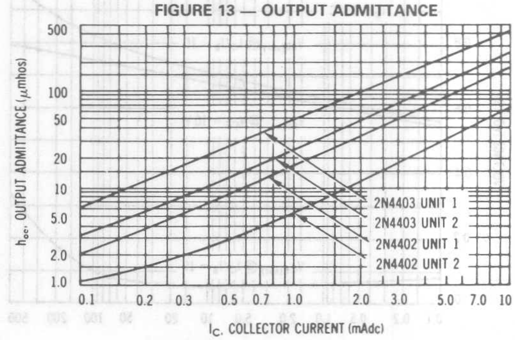
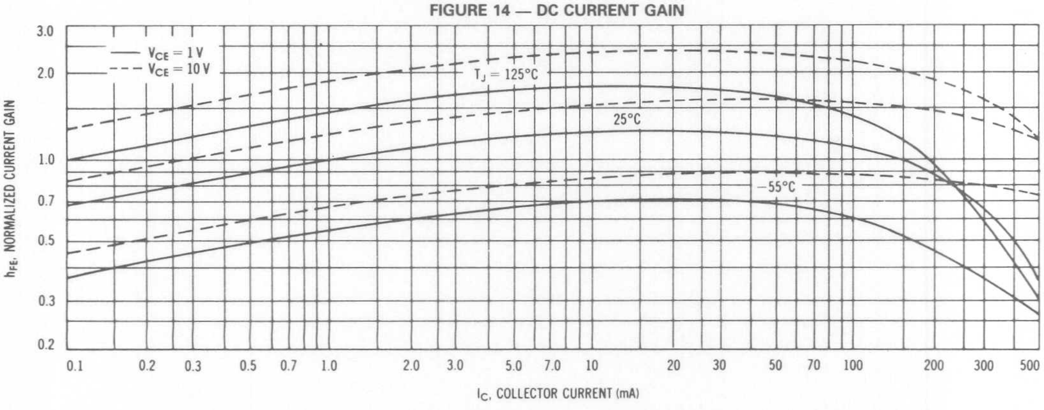


FIGURE 13 — OUTPUT ADMITTANCE



STATIC CHARACTERISTICS

FIGURE 14 — DC CURRENT GAIN



2

FIGURE 15 — COLLECTOR SATURATION REGION

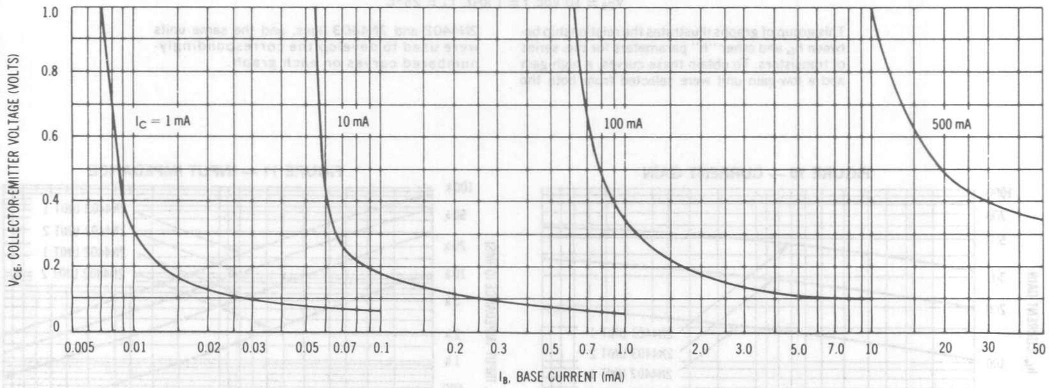


FIGURE 16 — "ON" VOLTAGES

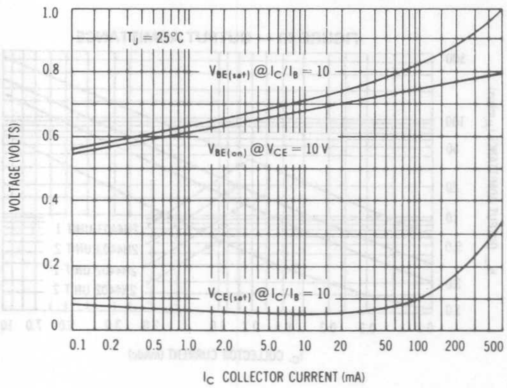
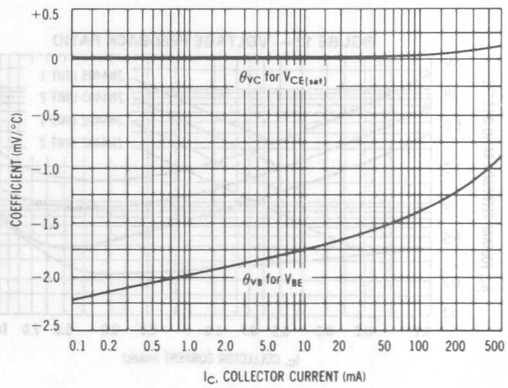
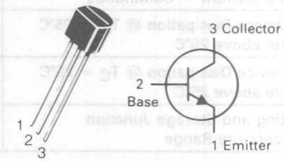


FIGURE 17 — TEMPERATURE COEFFICIENTS



2N4409
2N4410

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

NPN SILICON

Refer to 2N5550 for graphs.

MAXIMUM RATINGS

Rating	Symbol	2N4409	2N4410	Unit
Collector-Emitter Voltage	V_{CEO}	50	80	Vdc
Collector-Base Voltage	V_{CBO}	80	120	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	250		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

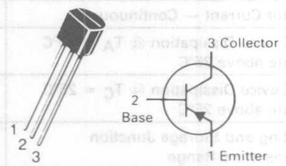
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)	2N4409 2N4410	$V_{(BR)CEO}$	50 80	— —	Vdc
Collector-Emitter Breakdown Voltage (I_C = 500 μAdc, V_{BE} = 5.0 Vdc, R_{BE} = 8.2 kohms)	2N4409 2N4410	$V_{(BR)CEX}$	80 120	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	2N4409 2N4410	$V_{(BR)CBO}$	80 120	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 60 Vdc, I_E = 0) (V_{CB} = 60 Vdc, I_E = 0, T_A = 100°C) (V_{CB} = 100 Vdc, I_E = 0) (V_{CB} = 100 Vdc, I_E = 0, T_A = 100°C)	2N4409 2N4409 2N4410 2N4410	I_{CBO}	— — — —	0.01 1.0 0.01 1.0	μAdc
Emitter Cutoff Current (V_{BE} = 4.0 Vdc, I_C = 0)		I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc)		h_{FE}	60 60	— 400	—
Collector-Emitter Saturation Voltage (I_C = 1.0 mAdc, I_B = 0.1 mAdc)		$V_{CE(sat)}$	—	0.2	Vdc
Base-Emitter Saturation Voltage (I_C = 1.0 mAdc, I_B = 0.1 mAdc)		$V_{BE(sat)}$	—	0.8	Vdc
Base-Emitter On Voltage (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)		$V_{BE(on)}$	—	0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 30 MHz)		f_T	60	300	MHz
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 140 kHz, emitter guarded)		C_{cb}	—	12	pF
Emitter-Base Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 140 kHz, collector guarded)		C_{eb}	—	50	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) $f_T = |h_{fe}| \cdot f_{test}$.

2N5086
2N5087

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector-Base Voltage	V_{CBO}	50	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	50	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	357	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 1.0$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	50	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)		$V_{(BR)CBO}$	50	—	Vdc
Collector Cutoff Current ($V_{CB} = 10$ Vdc, $I_E = 0$) ($V_{CB} = 35$ Vdc, $I_E = 0$)		I_{CBO}	 — —	 10 50	nAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)		I_{EBO}	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 100$ μAdc, $V_{CE} = 5.0$ Vdc)	 2N5086 2N5087	h_{FE}	 150 250	 500 800	—
($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc)	2N5086 2N5087		150 250	—	
($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc)(2)	2N5086 2N5087		150 250	—	
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)		$V_{CE(sat)}$	—	0.3	Vdc
Base-Emitter On Voltage ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc)		$V_{BE(on)}$	—	0.85	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 500$ μAdc, $V_{CE} = 5.0$ Vdc f = 20 MHz)		f_T	40		MHz
Collector-Base Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 100 kHz)		C_{cb}	—	4.0	pF
Small-Signal Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz)	 2N5086 2N5087	h_{fe}	 150 250	 600 900	—
Noise Figure ($I_C = 20$ μAdc, $V_{CE} = 5.0$ Vdc, $R_S = 10$ k ohms, f = 10 Hz to 15.7 kHz)	 2N5086 2N5087	NF	 — —	 3.0 2.0	dB
($I_C = 100$ μAdc, $V_{CE} = 5.0$ Vdc, $R_S = 3.0$ k ohms, f = 1.0 kHz)	2N5086 2N5087		— —	3.0 2.0	

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

TYPICAL NOISE CHARACTERISTICS
(V_{CE} = 5.0 Vdc, T_A = 25°C)

FIGURE 1 — NOISE VOLTAGE

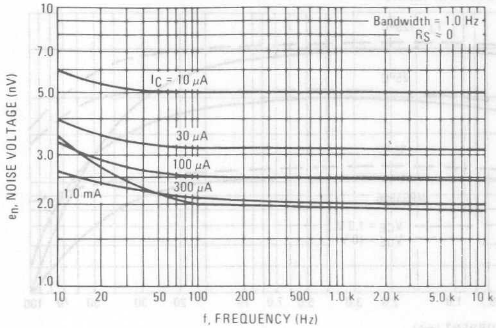
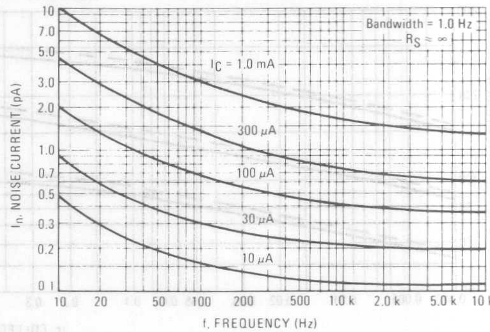


FIGURE 2 — NOISE CURRENT



NOISE FIGURE CONTOURS
(V_{CE} = 5.0 Vdc, T_A = 25°C)

FIGURE 3 — NARROW BAND, 100 Hz

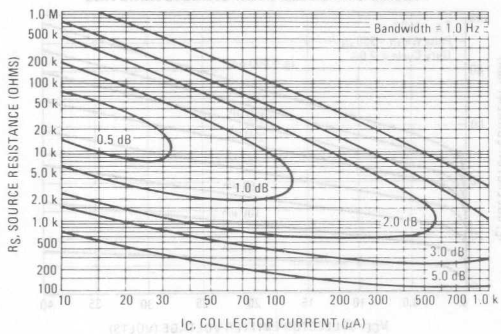


FIGURE 4 — NARROW BAND, 1.0 KHz

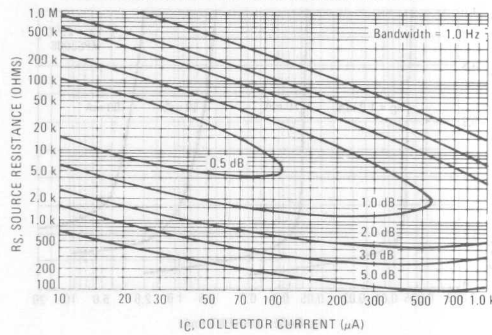
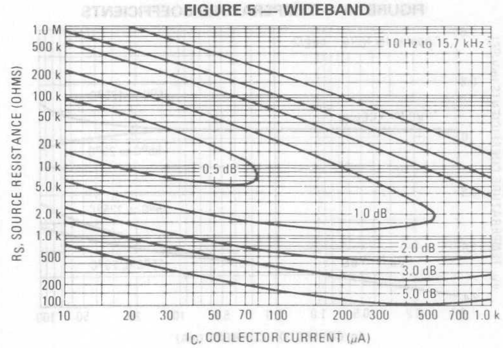


FIGURE 5 — WIDEBAND



Noise Figure is Defined as:

$$NF = 20 \log_{10}\left[\frac{e_n^2 + 4KTR_S + I_n^2 R_S^2}{4KTR_S}\right]^{1/2}$$

e_n = Noise Voltage of the Transistor referred to the input. (Figure 3)
I_n = Noise Current of the transistor referred to the input (Figure 4)
K = Boltzman's Constant (1.38×10^{-23} j/°K)
T = Temperature of the Source Resistance (°K)
R_S = Source Resistance (Ohms)

TYPICAL STATIC CHARACTERISTICS

FIGURE 6 — DC CURRENT GAIN

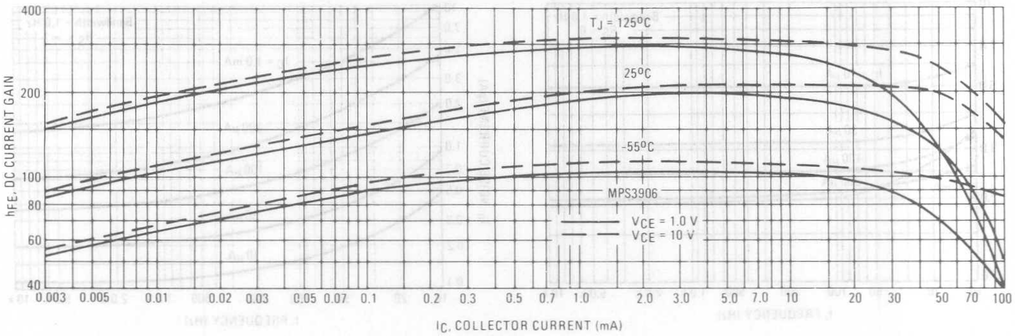


FIGURE 7 — COLLECTOR SATURATION REGION

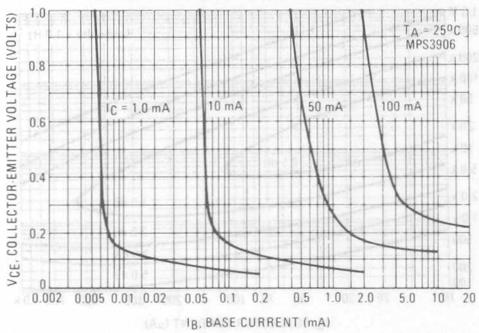


FIGURE 8 — COLLECTOR CHARACTERISTICS

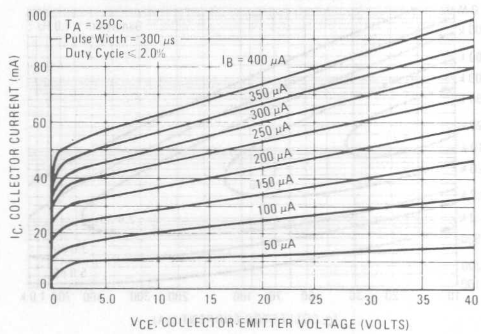


FIGURE 9 — "ON" VOLTAGES

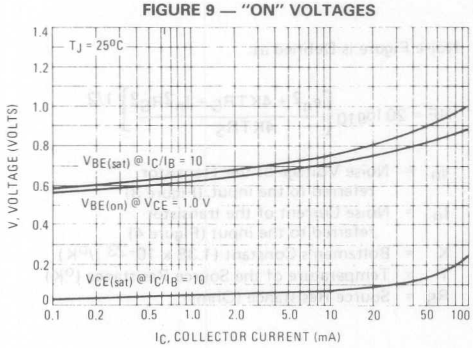
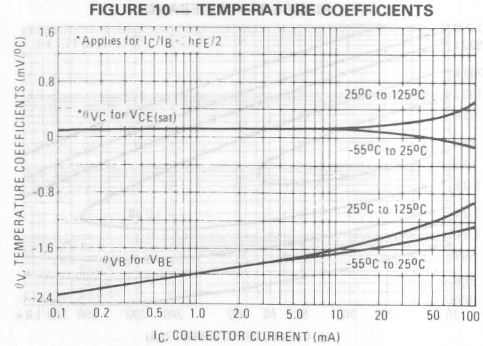


FIGURE 10 — TEMPERATURE COEFFICIENTS



TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 11 — TURN-ON TIME

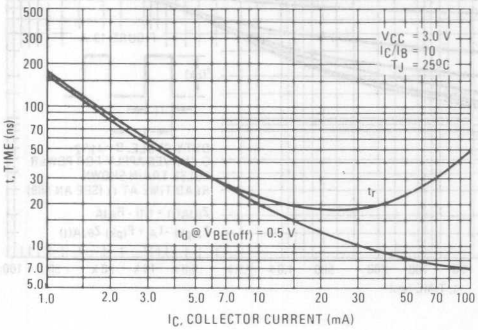


FIGURE 12 — TURN-OFF TIME

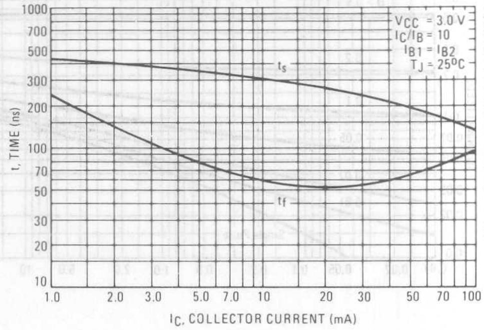


FIGURE 13 — CURRENT-GAIN — BANDWIDTH PRODUCT

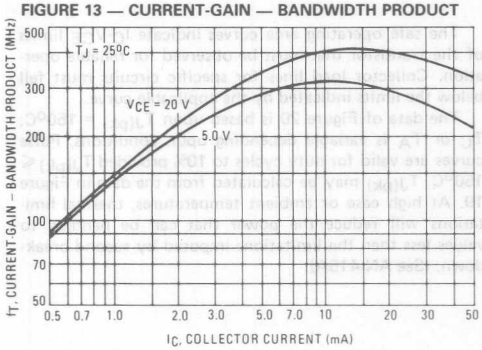


FIGURE 14 — CAPACITANCE

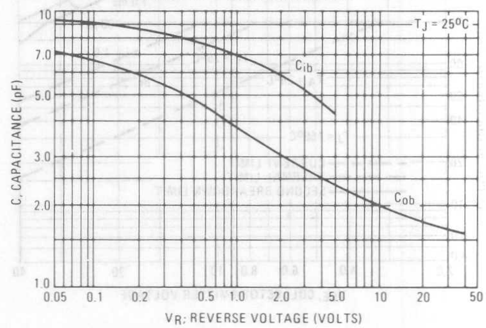


FIGURE 15 — INPUT IMPEDANCE

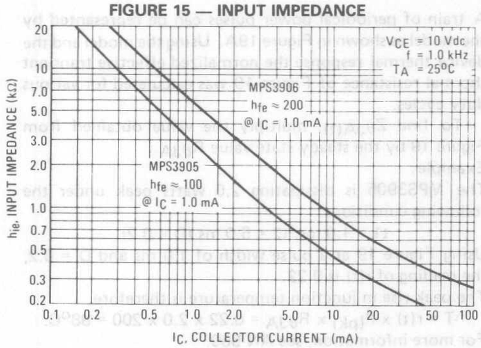
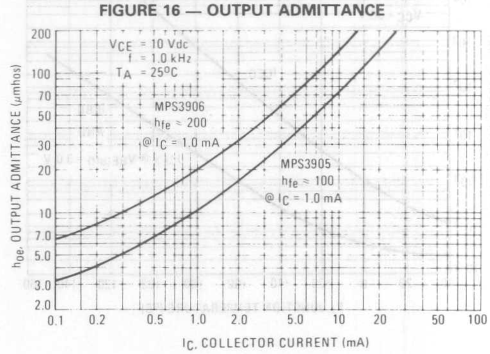


FIGURE 16 — OUTPUT ADMITTANCE



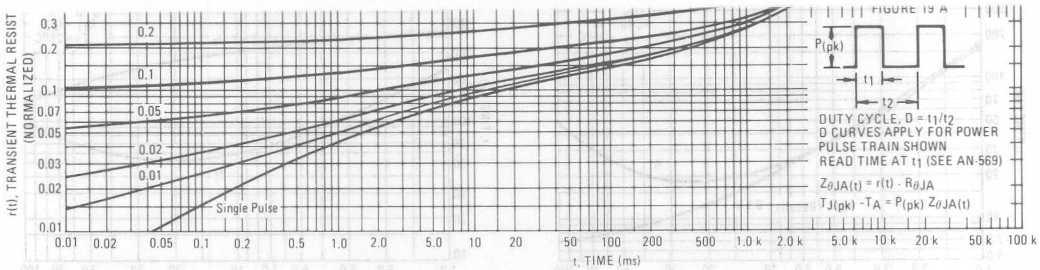
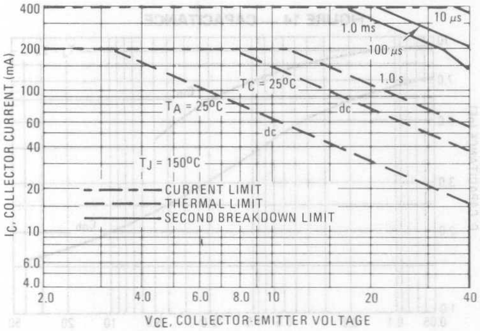


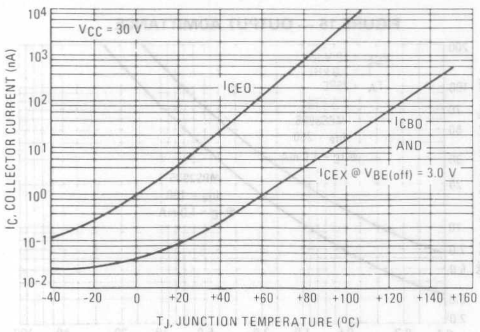
FIGURE 18 — ACTIVE-REGION SAFE OPERATING AREA



The safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 20 is based upon $T_{J(pk)} = 150^oC$; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leqslant 150^oC$. $T_{J(pk)}$ may be calculated from the data in Figure 19. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. (See AN-415A).

FIGURE 19 — TYPICAL COLLECTOR LEAKAGE CURRENT



DESIGN NOTE: USE OF THERMAL RESPONSE DATA

A train of periodical power pulses can be represented by the model as shown in Figure 19A. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 19 was calculated for various duty cycles.

To find $Z_{\theta JA(t)}$, multiply the value obtained from Figure 19 by the steady state value $R_{\theta JA}$.

Example:

The MPS3905 is dissipating 2.0 watts peak under the following conditions:

$t1 = 1.0$ ms, $t2 = 5.0$ ms $(D = 0.2)$

Using Figure 19 at a pulse width of 1.0 ms and D = 0.2, the reading of r(t) is 0.22.

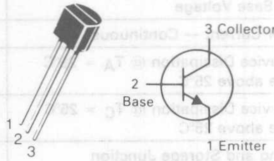
The peak rise in junction temperature is therefore

$\Delta T = r(t) \times P_{(pk)} \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88^oC.$

For more information, see AN-569.

2N5088
2N5089

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MPSA18 for graphs.

MAXIMUM RATINGS

Rating	Symbol	2N5088	2N5089	Unit
Collector-Emitter Voltage	V_{CEO}	30	25	Vdc
Collector-Base Voltage	V_{CBO}	35	30	Vdc
Emitter-Base Voltage	V_{EBO}	4.5		Vdc
Collector Current — Continuous	I_C	50		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	357	°C/W

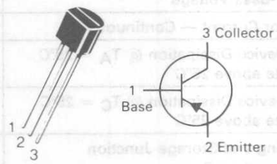
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 1.0 mAdc, I_B = 0)	2N5088 2N5089	$V_{(BR)CEO}$	30 25	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	2N5088 2N5089	$V_{(BR)CBO}$	35 30	—	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0) (V_{CB} = 15 Vdc, I_E = 0)	2N5088 2N5089	I_{CBO}	— —	50 50	nAdc
Emitter Cutoff Current ($V_{EB(off)}$ = 3.0 Vdc, I_C = 0) ($V_{EB(off)}$ = 4.5 Vdc, I_C = 0)		I_{EBO}	— —	50 100	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	2N5088 2N5089	h_{FE}	300 400	900 1200	—
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	2N5088 2N5089		350 450	— —	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)(2)	2N5088 2N5089		300 400	— —	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter On Voltage (I_C = 10 mAdc, V_{CE} = 5.0 Vdc)(2)		$V_{BE(on)}$	—	0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 500 μAdc, V_{CE} = 5.0 Vdc, f = 20 MHz)		f_T	50	—	MHz
Collector-Base Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz)		C_{cb}	—	4.0	pF
Emitter-Base Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{eb}	—	10	pF
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	2N5088 2N5089	h_{fe}	350 450	1400 1800	—
Noise Figure (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 kohms, f = 10 Hz to 15.7 kHz)	2N5088 2N5089	NF	— —	3.0 2.0	dB

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.
(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2N5208

CASE 29-04, STYLE 2
TO-92 (TO-226AA)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	50	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	65 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

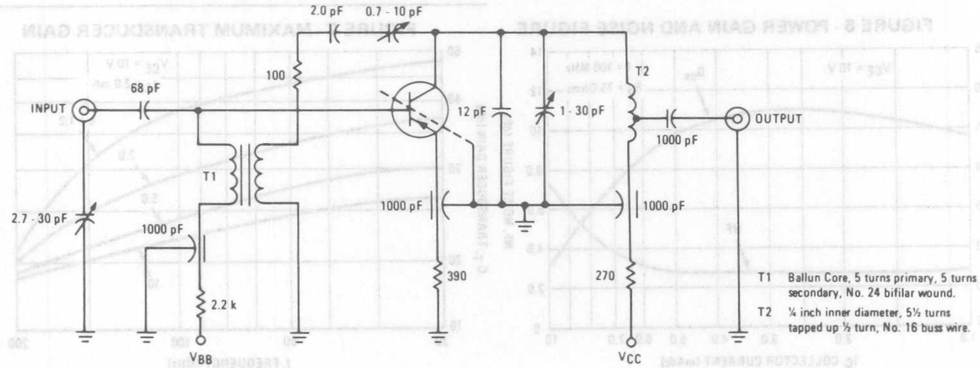
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	357	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	25	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.1$ mAdc, $I_E = 0$)	$V_{(BR)CBO}$	30	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 10$ Vdc, $I_E = 0$)	I_{CBO}	—	10	nAdc
Emitter Cutoff Current ($V_{BE} = 2.0$ Vdc, $I_C = 0$)	I_{EBO}	—	100	nAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	20	120	—
Base-Emitter On Voltage ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc)	$V_{BE(on)}$	—	0.85	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	300	1200	MHz
Input Capacitance ($V_{BE} = 2.0$ Vdc, $I_C = 0$, f = 1.0 MHz)	C_{ibo}	—	4.0	pF
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{cb}	—	1.0	pF
Collector Base Time Constant ($I_E = 2.0$ mAdc, $V_{CB} = 10$ Vdc, f = 31.8 MHz)	$rb'C_c$	—	10	ps
Noise Figure ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc, $R_S = 75$ ohms, f = 100 MHz, BW = 1.0 MHz)	NF		3.0	dB
FUNCTIONAL TEST				
Amplifier Power Gain ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	G_{pe}	22		dB

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

FIGURE 1 - 100 MHz POWER GAIN AND NOISE FIGURE TEST CIRCUIT



COMMON-EMITTER Y PARAMETERS (Polar Plots)

$V_{CE} = 10$ Vdc, $T_A = 25^oC$

FIGURE 2 - INPUT ADMITTANCE

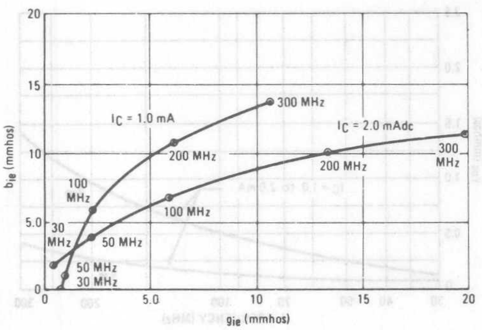


FIGURE 3 - OUTPUT ADMITTANCE

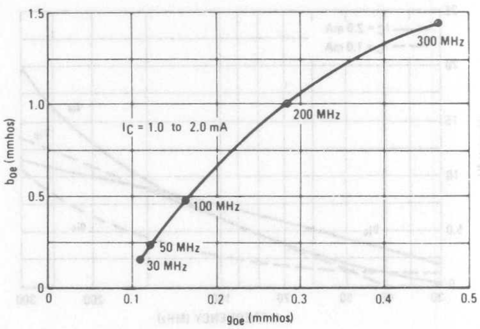


FIGURE 4 - FORWARD TRANSFER ADMITTANCE

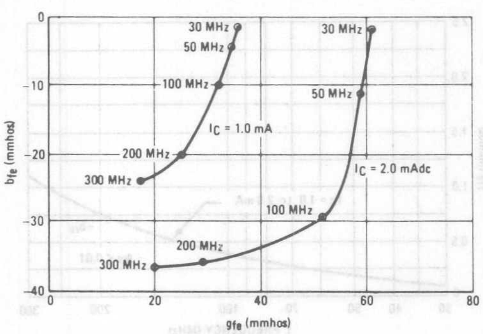
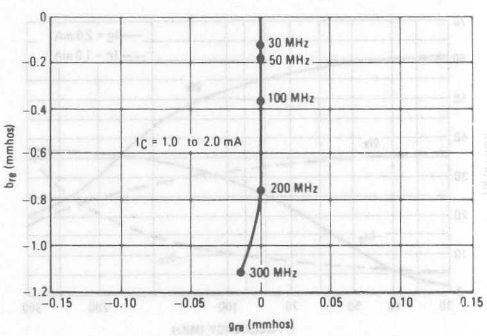


FIGURE 5 - REVERSE TRANSFER ADMITTANCE



2

STABILITY FACTOR CURVE

FIGURE 6 - POWER GAIN AND NOISE FIGURE

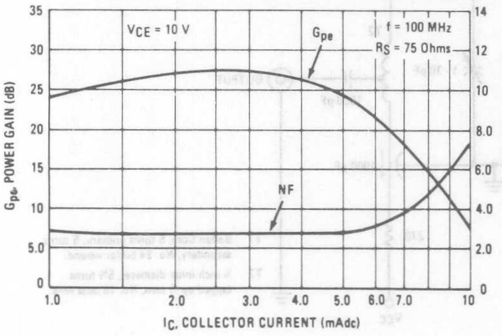
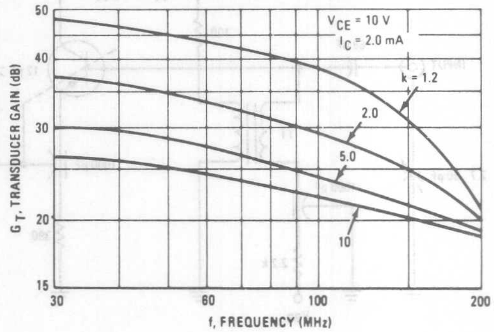


FIGURE 7 - MAXIMUM TRANSDUCER GAIN



COMMON-EMITTER Y PARAMETERS vs FREQUENCY

V_{CE} = 10 Vdc, T_A = 25°C

FIGURE 8 - INPUT ADMITTANCE

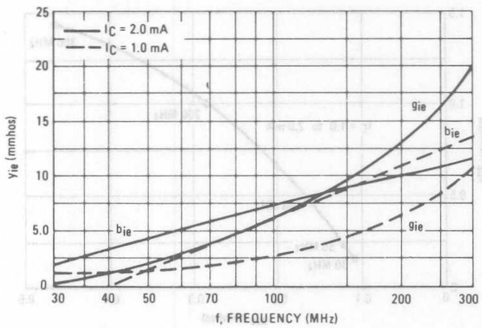


FIGURE 9 - OUTPUT ADMITTANCE

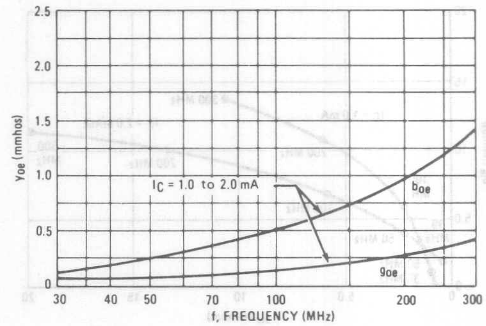


FIGURE 10 - FORWARD TRANSFER ADMITTANCE

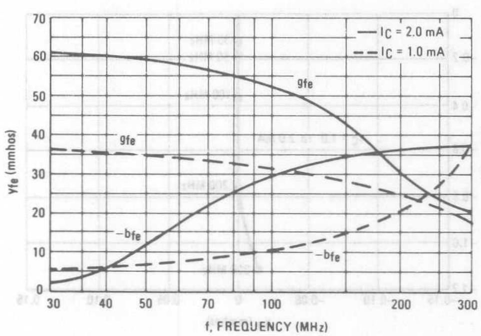
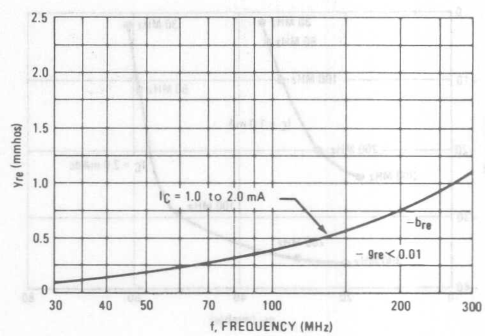


FIGURE 11 - REVERSE TRANSFER ADMITTANCE



STABILITY FACTOR CURVES

FIGURE 12 - OPTIMUM SOURCE ADMITTANCE

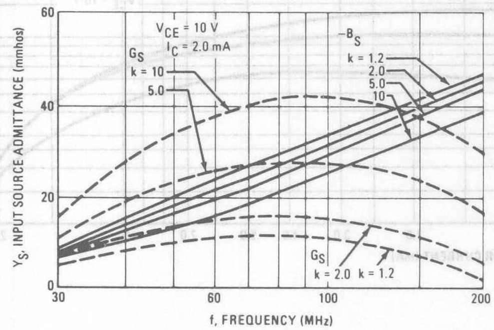
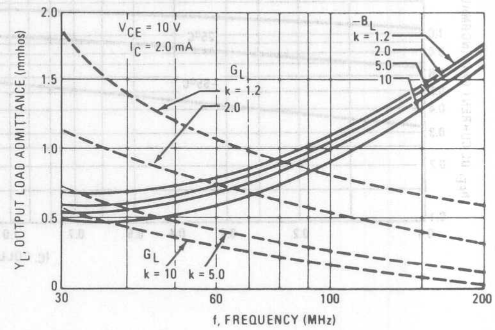


FIGURE 13 - OPTIMUM LOAD ADMITTANCE



Vhen a potentially unstable device is operated without feedback, there is an infinite number of combinations of ource and load admittance associated with any given circuit stability factor (k). Equations have been developed for etermining the optimum source and load admittance for maximum gain. Figures 7, 12 and 13 provide a solution to he equations for the 2N5208.

NOISE FIGURE

FIGURE 14 - FREQUENCY EFFECTS

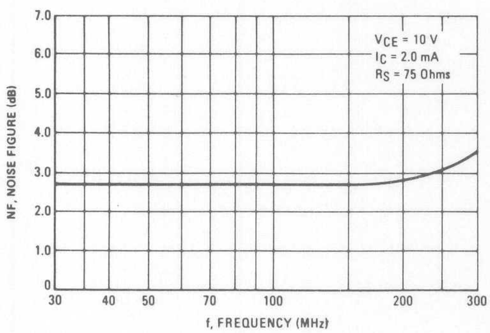


FIGURE 15 - SOURCE RESISTANCE EFFECTS

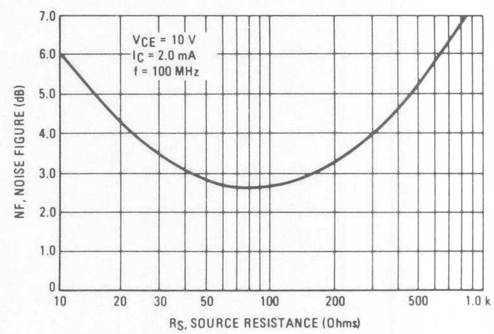


FIGURE 16 - CURRENT-GAIN — BANDWIDTH PRODUCT

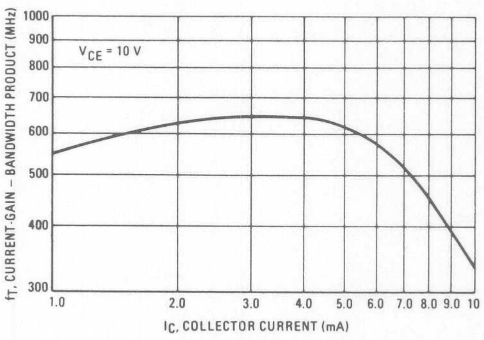
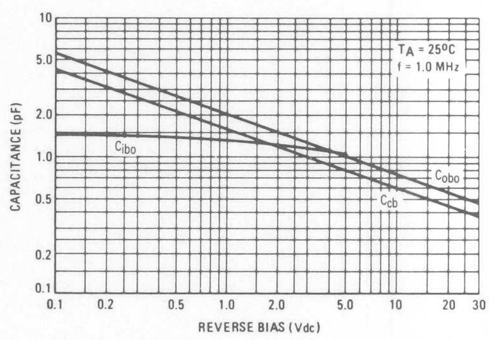
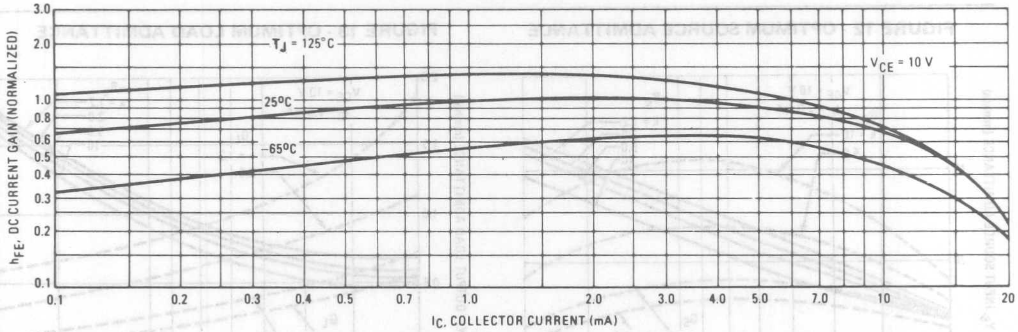


FIGURE 17 - CAPACITANCES



2

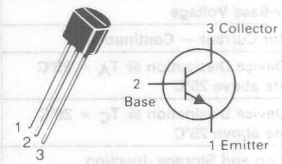
FIGURE 18 - DC CURRENT GAIN



2N5209
2N5210

2

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MPSA18 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector-Base Voltage	V_{CBO}	50	Vdc
Emitter-Base Voltage	V_{EBO}	4.5	Vdc
Collector Current — Continuous	I_C	50	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

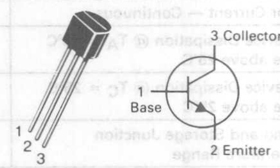
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)		$V_{(BR)CEO}$	50	—	Vdc
Collector-Base Breakdown Voltage (I_C = 0.1 mAdc, I_E = 0)		$V_{(BR)CBO}$	50	—	Vdc
Collector Cutoff Current (V_{CB} = 35 Vdc, I_E = 0)		I_{CBO}	—	50	nAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)		I_{EBO}	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	2N5209 2N5210	h_{FE}	100 200	300 600	—
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	2N5209 2N5210		150 250	— —	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)(2)	2N5209 2N5210		150 250	— 	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{CE(sat)}$	—	0.7	Vdc
Base-Emitter On Voltage (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)		$V_{BE(on)}$	—	0.85	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 500 μAdc, V_{CE} = 5.0 Vdc, f = 20 MHz)		f_T	30		MHz
Collector-Base Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz)		C_{cb}	—	4.0	pF
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	2N5209 2N5210	h_{fe}	150 250	600 900	—
Noise Figure (I_C = 20 μAdc, V_{CE} = 5.0 Vdc, R_S = 22 k ohms, f = 10 Hz to 15.7 kHz)	2N5209 2N5210	NF	— —	3.0 2.0	dB
(I_C = 20 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 k ohms, f = 1.0 kHz)	2N5209 2N5210		— —	4.0 3.0	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.
(2) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

2

2N5222

CASE 29-04, STYLE 2
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Base Voltage	V_{CBO}	20	Vdc
Emitter-Base Voltage	V_{EBO}	2.0	Vdc
Collector Current — Continuous	I_C	50	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	357	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	15	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	20		Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	2.0		Vdc
Collector Cutoff Current ($V_{CB} = 10$ Vdc, $I_E = 0$)	I_{CBO}	—	100	nAdc
Emitter Cutoff Current ($V_{BE} = 2.0$ Vdc, $I_C = 0$)	I_{EBO}	—	100	nAdc
ON CHARACTERISTICS				
DC Current Gain(2) ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	20	150	—
Collector-Emitter Saturation Voltage ($I_C = 4.0$ mAdc, $I_B = 400\ \mu$Adc)	$V_{CE(sat)}$	—	1.0	Vdc
Base-Emitter On Voltage ($I_C = 4.0$ mAdc, $I_B = 400\ \mu$Adc)	$V_{BE(on)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)	f_T	450		MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{cb}	—	1.3	pF
Small-Signal Current Gain ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	20	300	—

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.
(2) Pulse Test: Pulse Width ≈ 300 μs, Duty Cycle ≈ 2.0%.

COMMON-BASE y PARAMETERS versus FREQUENCY
(V_{CB} = 10 Vdc, I_C = 4.0 mAdc, T_A = 25°C)

y_{ib}, INPUT ADMITTANCE

FIGURE 1 – RECTANGULAR FORM

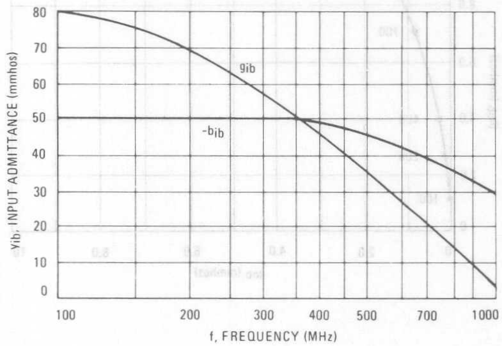
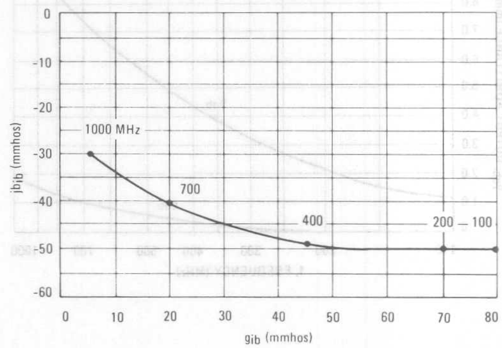


FIGURE 2 – POLAR FORM



y_{fb}, FORWARD TRANSFER ADMITTANCE

FIGURE 3 – RECTANGULAR FORM

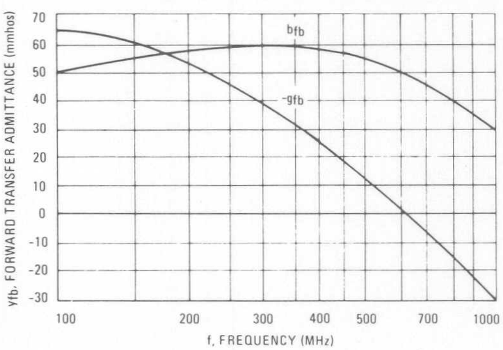
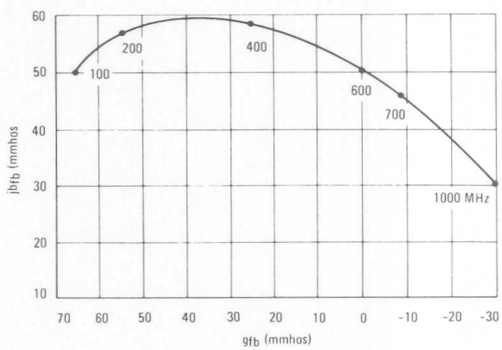


FIGURE 4 – POLAR FORM



COMMON-BASE y PARAMETERS versus FREQUENCY
(V_{CB} = 10 Vdc, I_C = 4.0 mAdc, T_A = 25°C)

y_{rb}, REVERSE TRANSFER ADMITTANCE

FIGURE 5 – RECTANGULAR FORM

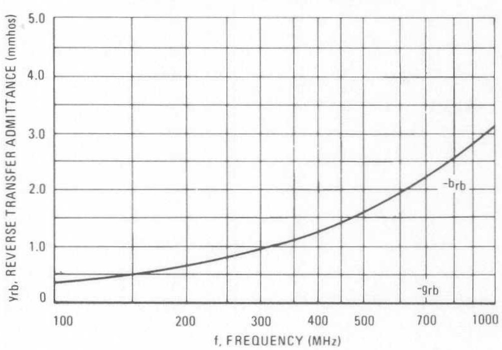
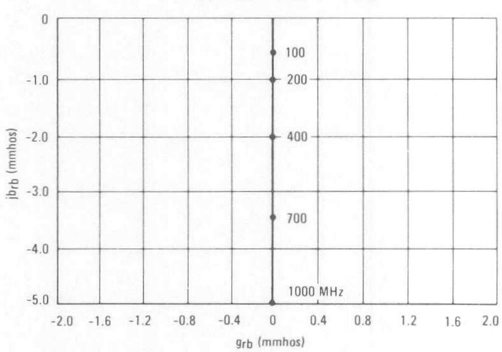


FIGURE 6 – POLAR FORM



y_{ob}, OUTPUT ADMITTANCE

FIGURE 7 – RECTANGULAR FORM

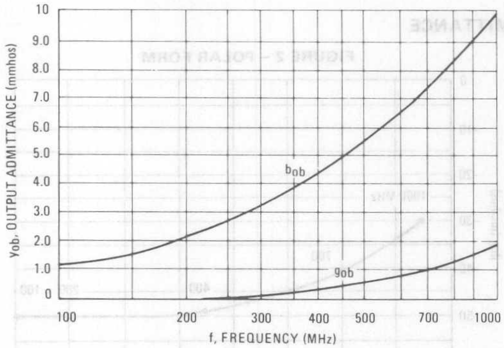
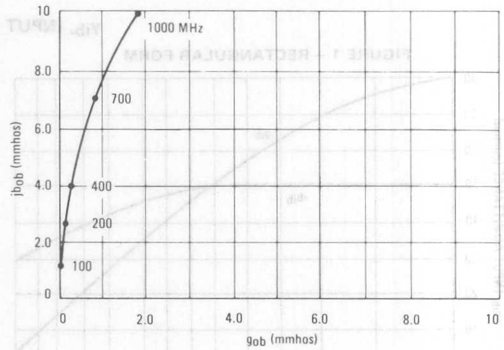
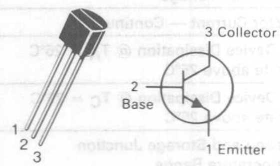


FIGURE 8 – POLAR FORM



2N5223

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N3903 for graphs.

2

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	20	Vdc
Collector-Base Voltage	V_{CBO}	25	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	100	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	357	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

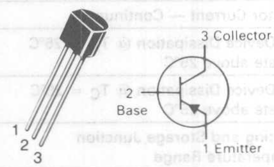
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	20	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	25		Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	3.0		Vdc
Collector Cutoff Current (V_{CB} = 10 Vdc, I_E = 0)	I_{CBO}	—	100	nAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)	I_{EBO}	—	500	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 2.0 mAdc, V_{CE} = 10 Vdc)	h_{FE}	50	800	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{CE(sat)}$	—	0.7	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{BE(sat)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)	f_T	150	—	MHz
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	—	4.0	pF
Small-Signal Current Gain (I_C = 2.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{fe}	50	1600	—

2

2N5226

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	25	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	500	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	357	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

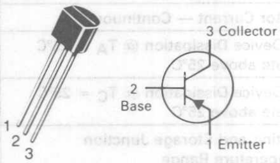
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	25	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	25	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_C = 0$)	I_{CBO}	—	300	nAdc
Emitter Cutoff Current ($V_{BE} = 4.0$ Vdc, $I_C = 0$)	I_{EBO}	—	500	nAdc
ON CHARACTERISTICS(2)				
DC Current Gain ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	 25 30	 — 600	—
Collector-Emitter Saturation Voltage ($I_C = 100$ mAdc, $I_B = 10$ mAdc)	$V_{CE(sat)}$	—	0.8	Vdc
Base-Emitter Saturation Voltage ($I_C = 100$ mAdc, $I_B = 10$ mAdc)	$V_{BE(sat)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 20$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)	f_T	50	—	MHz
Collector-Base Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{cb}	—	20	pF
Small-Signal Current Gain ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	30	1800	—

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	50	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

PNP SILICON

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}(1)$	200	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

Refer to 2N3905 for graphs.

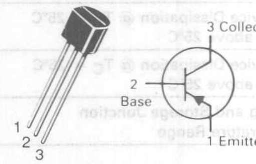
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	30	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	30	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 10$ Vdc, $I_E = 0$)	I_{CBO}	—	100	nAdc
Emitter Cutoff Current ($V_{BE} = 2.0$ Vdc, $I_C = 0$)	I_{EBO}	—	500	nAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 100$ μAdc, $V_{CE} = 10$ Vdc) ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	 30 50	— 700	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	0.4	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)	f_T	100	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{cb}	—	5.0	pF
Small-Signal Current Gain ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	50	1500	—

2

2N5400
2N5401

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	2N5400	2N5401	Unit
Collector-Emitter Voltage	V_{CEO}	120	150	Vdc
Collector-Base Voltage	V_{CBO}	130	160	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	600		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12.0		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)	 2N5400 2N5401	$V_{(BR)CEO}$	 120 150	 — —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	 2N5400 2N5401	$V_{(BR)CBO}$	 130 160	 — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 100 Vdc, I_E = 0) (V_{CB} = 120 Vdc, I_E = 0) (V_{CB} = 100 Vdc, I_E = 0, T_A = 100°C) (V_{CB} = 120 Vdc, I_E = 0, T_A = 100°C)	 2N5400 2N5401 2N5400 2N5401	I_{CBO}	 — — — —	 100 50 100 50	 nAdc μAdc
Emitter Cutoff Current (V_{EB} = 3.0 Vdc, I_C = 0)		I_{EBO}	—	50	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc) (I_C = 10 mAdc, V_{CE} = 5.0 Vdc) (I_C = 50 mAdc, V_{CE} = 5.0 Vdc)	 2N5400 2N5401 2N5400 2N5401 2N5400 2N5401	h_{FE}	 30 50 40 60 40 50	 — — 180 240 — —	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{CE(sat)}$	 — —	 0.20 0.5	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{BE(sat)}$	 — —	 1.0 1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 Mhz)	 2N5400 2N5401	f_T	 100 100	 400 300	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	6.0	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N5400 2N5401	h_{fe}	30 40	200 200	—
Noise Figure (I_C = 250 μAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 kohm, f = 10 Hz to 15.7 kHz)		NF	—	8.0	dB

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

FIGURE 1 — DC CURRENT GAIN

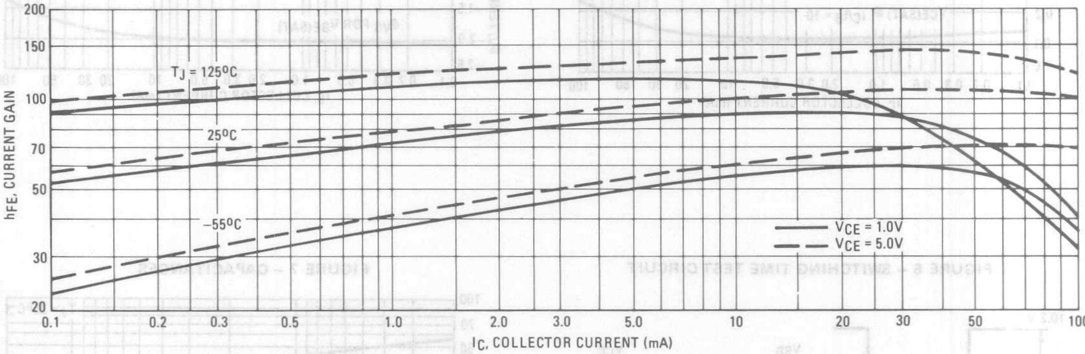


FIGURE 2 — COLLECTOR SATURATION REGION

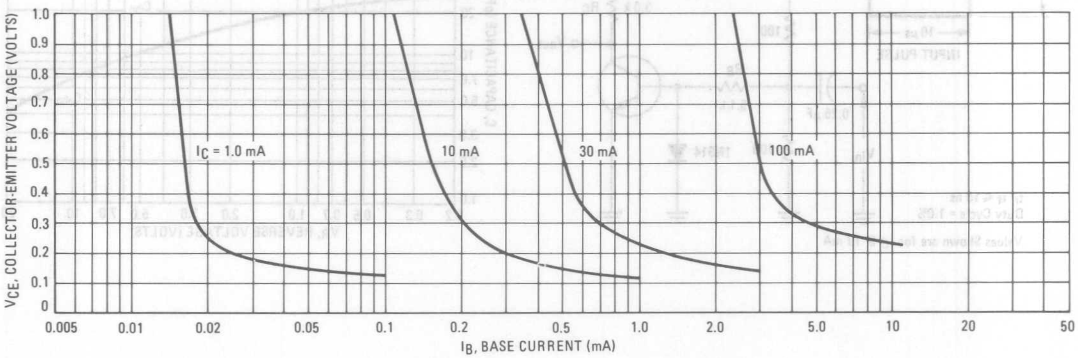


FIGURE 3 — COLLECTOR CUT-OFF REGION

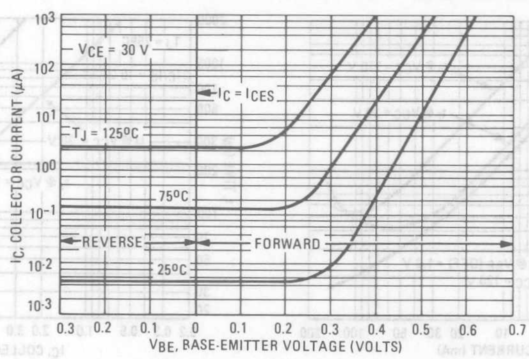


FIGURE 4 – "ON" VOLTAGES

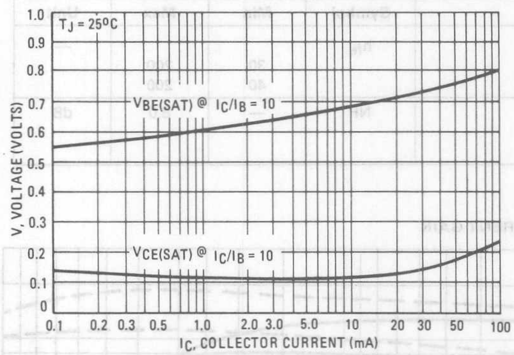


FIGURE 5 – TEMPERATURE COEFFICIENTS

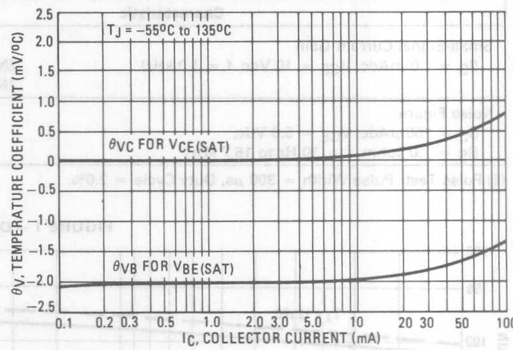


FIGURE 6 – SWITCHING TIME TEST CIRCUIT

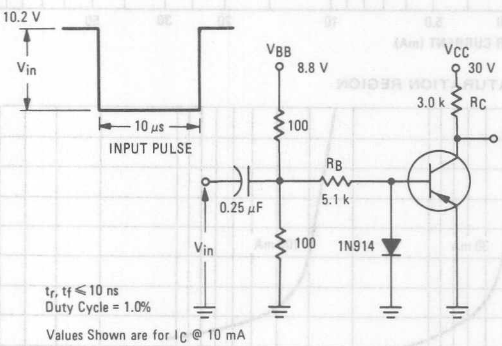


FIGURE 7 – CAPACITANCES

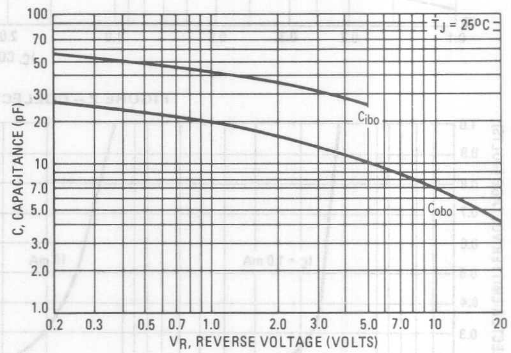


FIGURE 8 – TURN-ON TIME

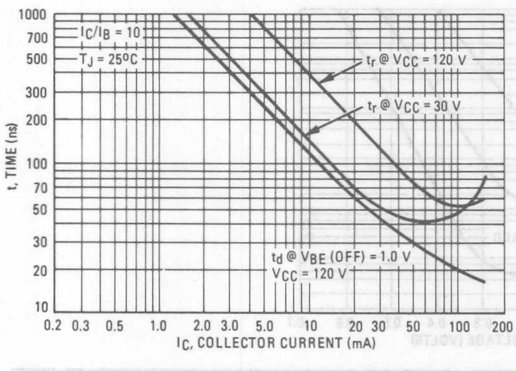
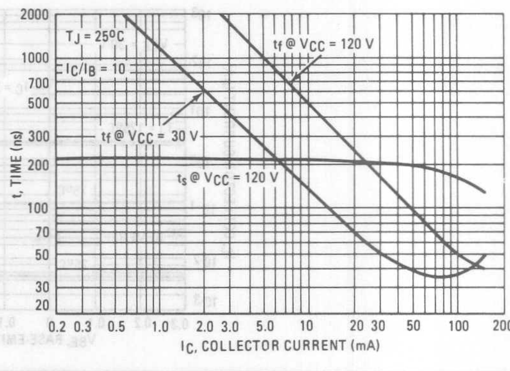
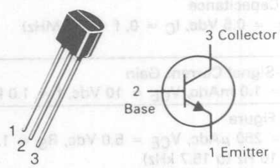


FIGURE 9 – TURN-OFF TIME



2N5550
2N5551

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	2N5550	2N5551	Unit
Collector-Emitter Voltage	V_{CEO}	140	160	Vdc
Collector-Base Voltage	V_{CBO}	160	180	Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	600		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	357	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 1.0 mAdc, I_B = 0)	 2N5550 2N5551	$V_{(BR)CEO}$	 140 160	 — —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	 2N5550 2N5551	$V_{(BR)CBO}$	 160 180	 — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current (V_{CB} = 100 Vdc, I_E = 0) (V_{CB} = 120 Vdc, I_E = 0) (V_{CB} = 100 Vdc, I_E = 0, T_A = 100°C) (V_{CB} = 120 Vdc, I_E = 0, T_A = 100°C)	 2N5550 2N5551 2N5550 2N5551	I_{CBO}	 — — — —	 100 50 100 50	 nAdc μAdc
Emitter Cutoff Current (V_{EB} = 4.0 Vdc, I_C = 0)		I_{EBO}	—	50	nAdc
ON CHARACTERISTICS(2)					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	 2N5550 2N5551	h_{FE}	 60 80	 — —	—
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	2N5550 2N5551		60 80	250 250	
(I_C = 50 mAdc, V_{CE} = 5.0 Vdc)	2N5550 2N5551		20 30	— —	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	 Both Types	$V_{CE(sat)}$	 —	 0.15	Vdc
(I_C = 50 mAdc, I_B = 5.0 mAdc)	2N5550 2N5551		— —	0.25 0.20	
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	 Both Types	$V_{BE(sat)}$	 —	 1.0	Vdc
(I_C = 50 mAdc, I_B = 5.0 mAdc)	2N5550 2N5551		— —	1.2 1.0	

(2) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

2

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	100	300	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	6.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	2N5550 2N5551	C_{ibo}	— —	30 20	pF
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{fe}	50	200	—
Noise Figure (I_C = 250 μAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 kohm, f = 10 Hz to 15.7 kHz)	2N5550 2N5551	NF	— —	10 8.0	dB

FIGURE 1 – DC CURRENT GAIN

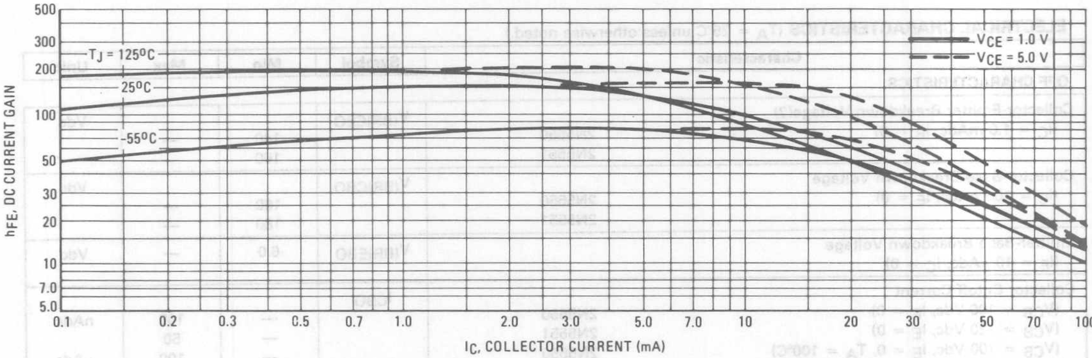


FIGURE 2 – COLLECTOR SATURATION REGION

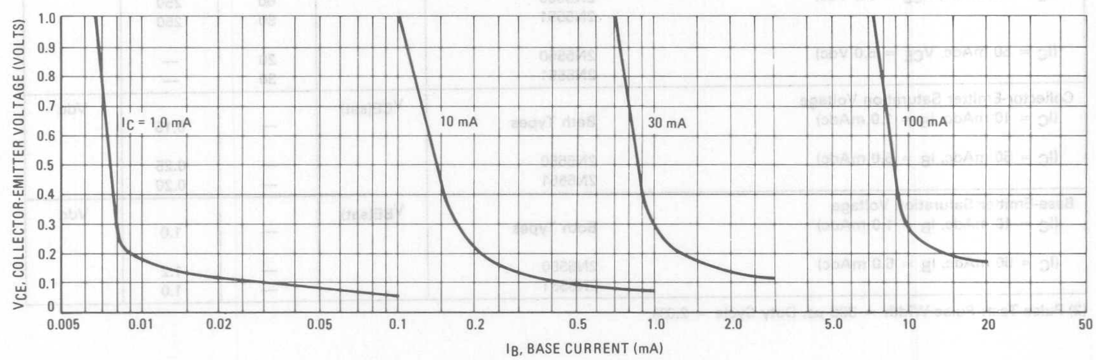


FIGURE 3 – COLLECTOR CUT-OFF REGION

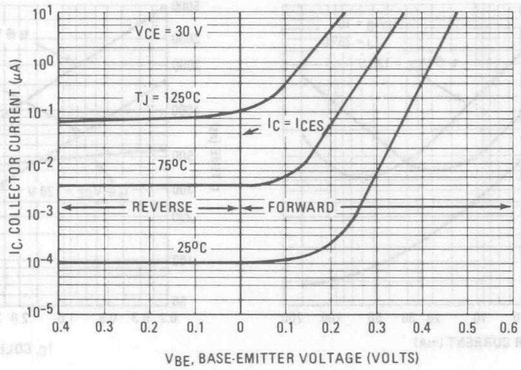


FIGURE 4 – "ON" VOLTAGES

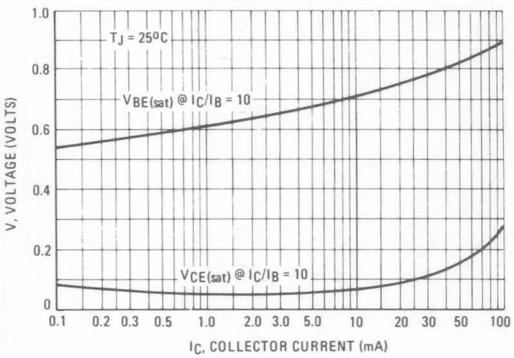


FIGURE 5 – TEMPERATURE COEFFICIENTS

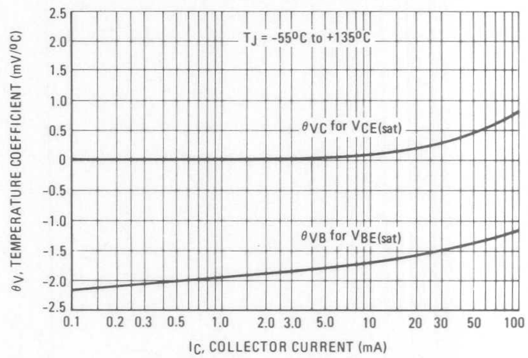


FIGURE 6 – SWITCHING TIME TEST CIRCUIT

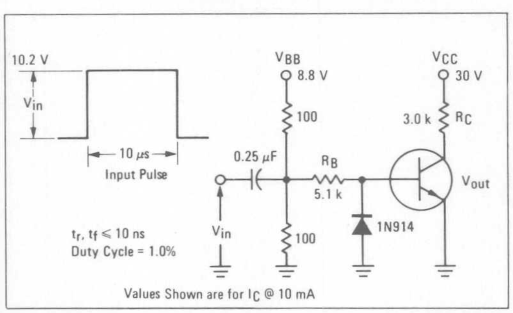
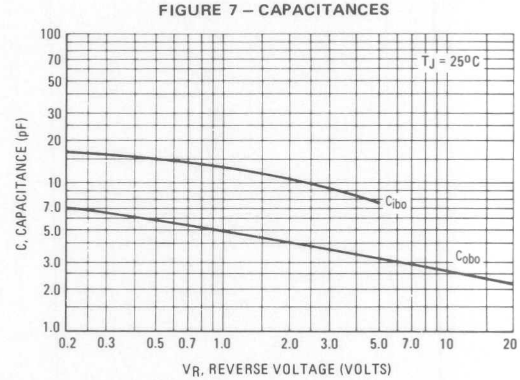
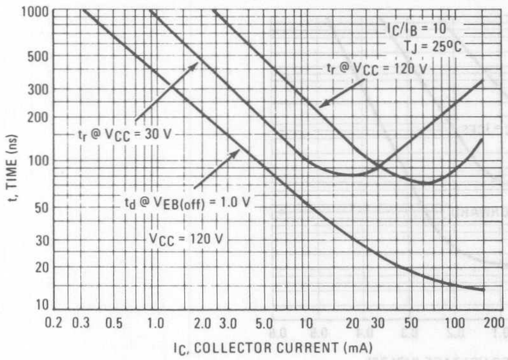
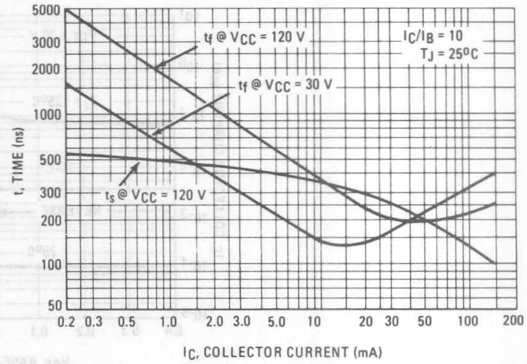


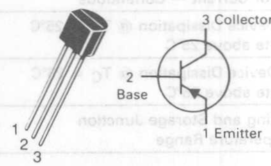
FIGURE 7 – CAPACITANCES




IC/IB = 10
TJ = 25°C
tr @ VCC = 120 V
tr @ VCC = 30 V
td @ VEB(off) = 1.0 V
VCC = 120 V
t, TIME (ns)
IC, COLLECTOR CURRENT (mA)


tf @ VCC = 120 V
IC/IB = 10
TJ = 25°C
tf @ VCC = 30 V
ts @ VCC = 120 V
t, TIME (ns)
IC, COLLECTOR CURRENT (mA)

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



SWITCHING TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Base Voltage	V_{CBO}	15	Vdc
Emitter-Base Voltage	V_{EBO}	4.5	Vdc
Collector Current — Continuous	I_C	50	mA
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8	Watts mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C
Lead Temperature	T_L	260	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

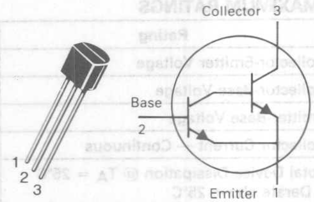
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage	(I_C = 3.0 mA)(1)	$V_{(BR)CEO}$	15	—	Vdc
Collector-Emitter Breakdown Voltage	(I_C = 100 μA)	$V_{(BR)CES}$	15	—	Vdc
Collector-Base Breakdown Voltage	(I_C = 100 μA)	$V_{(BR)CBO}$	15	—	Vdc
Emitter-Base Breakdown Voltage	(I_E = 100 μA)	$V_{(BR)EBO}$	4.5	—	Vdc
Collector Cutoff Current	(V_{CB} = 8.0 Vdc)	I_{CBO}	—	10	nA
Collector Cutoff Current	(V_{CE} = 8.0 Vdc) (V_{CE} = 8.0 Vdc, T_A = 125°C)	I_{CES}	— —	10 5.0	nA μA
Emitter Cutoff Current	(V_{BE} = 4.5 Vdc)	I_{EBO}	—	1.0	μA
ON CHARACTERISTICS					
DC Current Gain	(I_C = 1.0 mA, V_{CE} = 0.5 Vdc)(1) (I_C = 10 mA, V_{CE} = 0.3 Vdc)(1) (I_C = 50 mA, V_{CE} = 1.0 Vdc)(1) (I_C = 10 mA, V_{CE} = 0.3 Vdc, T_A = −55°C)	h_{FE}	35 50 40 20	— 120 —	—
Collector-Emitter Saturation Voltage(1)	(I_C = 1.0 mA, I_B = 0.1 mA) (I_C = 10 mA, I_B = 1.0 mA) (I_C = 50 mA, I_B = 5.0 mA)	$V_{CE(sat)}$	— — —	0.15 0.18 0.6	Vdc
Base-Emitter Saturation Voltage(1)	(I_C = 1.0 mA, I_B = 0.1 mA) (I_C = 10 mA, I_B = 1.0 mA) (I_C = 50 mA, I_B = 5.0 mA)	$V_{BE(sat)}$	— 0.75 —	0.8 0.95 1.5	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Collector-Base Capacitance (V_{CB} = 5.0 Vdc, f = 140 kHz)		C_{cb}	—	3.0	pF
Emitter-Base Capacitance (V_{BE} = 0.5 Vdc, f = 140 kHz)		C_{eb}	—	3.5	pF
Small-Signal Current Gain (I_C = 10 mA, V_{CE} = 10 Vdc, f = 100 MHz)		h_{fe}	8.5	—	—
SWITCHING CHARACTERISTICS					
Storage Time (I_C = 10 mA, I_{B1} ≈ I_{B2} ≈ 10 mA)		t_s	—	20	ns
Turn-On Time (I_C = 10 mA, I_B = 1.0 mA)		t_{on}	—	15	ns
Turn-Off Time (I_C = 10 mA, I_{B1} = I_{B2} = 1.0 mA)		t_{off}	—	20	ns

(1) Pulse Conditions: Pulse Length = 300 μs, Duty Cycle = 1.0%.

2

2N6426
2N6427

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



DARLINGTON TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	12	Vdc
Collector Current — Continuous	I_C	500	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	200	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

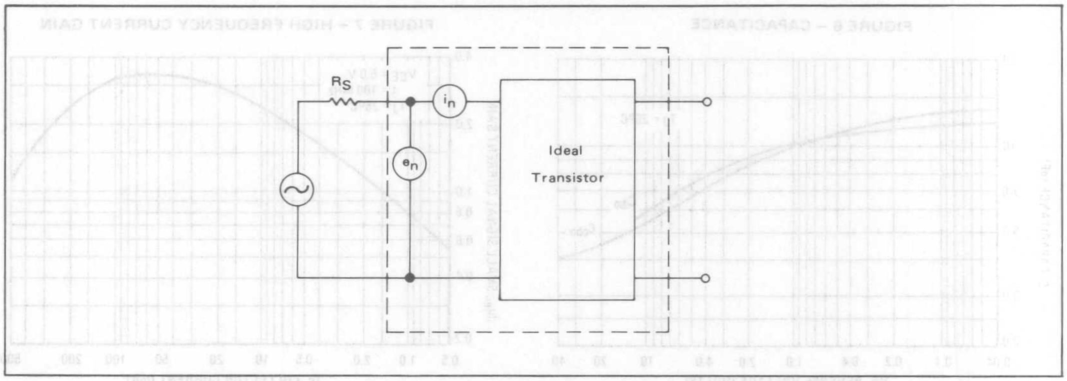
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)		$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)		$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	12	—	—	Vdc
Collector Cutoff Current (V_{CE} = 25 Vdc, I_B = 0)		I_{CEO}	—	—	1.0	μAdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)		I_{CBO}	—	—	50	nAdc
Emitter Cutoff Current (V_{BE} = 10 Vdc, I_C = 0)		I_{EBO}	—	—	50	nAdc
ON CHARACTERISTICS						
DC Current Gain(2)		h_{FE}				—
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	2N6426 2N6427		20,000 10,000	— —	200,000 100,000	
(I_C = 100 mAdc, V_{CE} = 5.0 Vdc)	2N6426 2N6427		30,000 20,000	— —	300,000 200,000	
(I_C = 500 mAdc, V_{CE} = 5.0 Vdc)	2N6426 2N6427		20,000 14,000	— —	200,000 140,000	
Collector-Emitter Saturation Voltage (I_C = 50 mAdc, I_B = 0.5 mAdc) (I_C = 500 mAdc, I_B = 0.5 mAdc)		$V_{CE(sat)}$	 — —	 0.71 0.9	 1.2 1.5	Vdc
Base-Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 0.5 mAdc)		$V_{BE(sat)}$	—	1.52	2.0	Vdc
Base-Emitter On Voltage (I_C = 50 mAdc, V_{CE} = 5.0 Vdc)		$V_{BE(on)}$	—	1.24	1.75	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	5.4	7.0	pF
Input Capacitance (V_{BE} = 1.0 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	10	15	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
Input Impedance (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	2N6426 2N6427	h_{ie}	100 50	— —	2000 1000	k Ω
Small-Signal Current Gain (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	2N6426 2N6427	h_{fe}	20,000 10,000	— —	— —	—
Current Gain — High Frequency (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)	2N6426 2N6427	$\|h_{fe}\|$	1.5 1.3	2.4 2.4	— —	—
Output Admittance (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)		h_{oe}	—	—	1000	μmhos
Noise Figure (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, R_S = 100 kΩ, f = 10 kHz to 15.7 kHz)		NF	—	3.0	10	dB

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 – TRANSISTOR NOISE MODEL



NOISE CHARACTERISTICS

(V_{CE} = 5.0 Vdc, T_A = 25°C)

FIGURE 2 – NOISE VOLTAGE

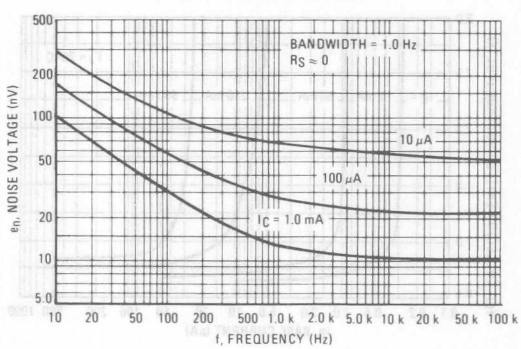
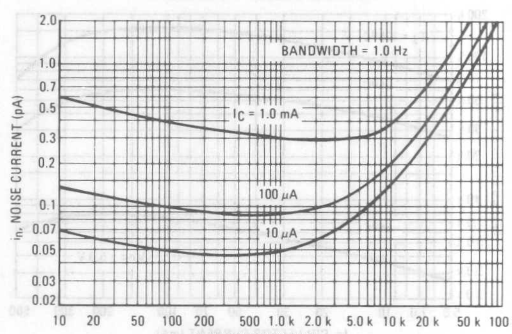
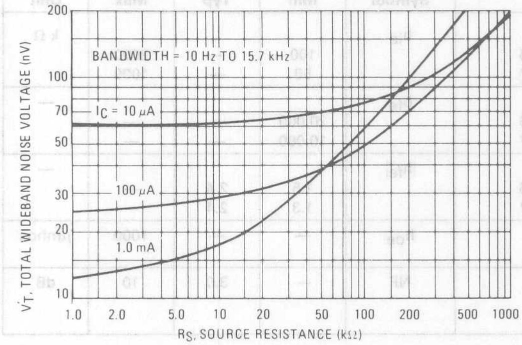
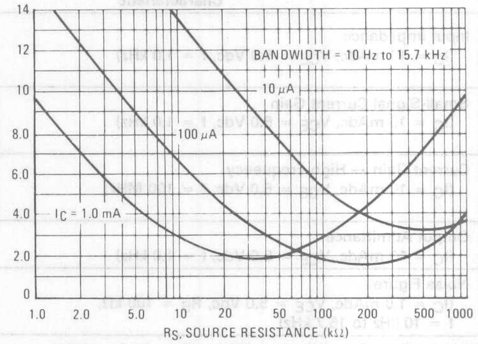


FIGURE 3 – NOISE CURRENT







SMALL-SIGNAL CHARACTERISTICS

FIGURE 6 – CAPACITANCE

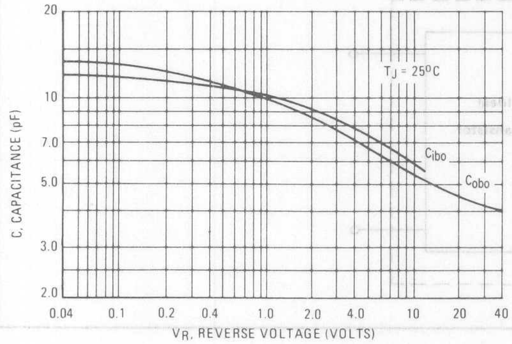


FIGURE 7 – HIGH FREQUENCY CURRENT GAIN

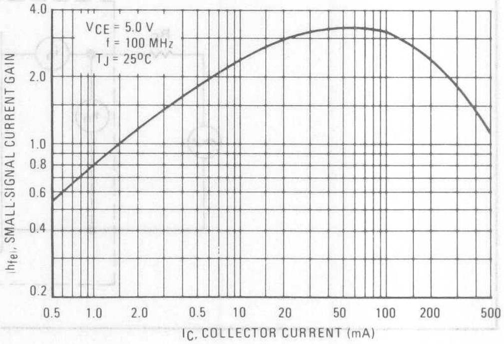


FIGURE 8 – DC CURRENT GAIN

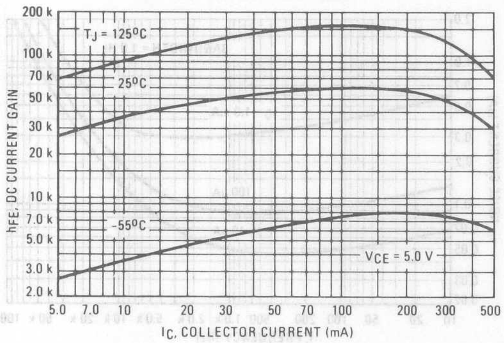


FIGURE 9 – COLLECTOR SATURATION REGION

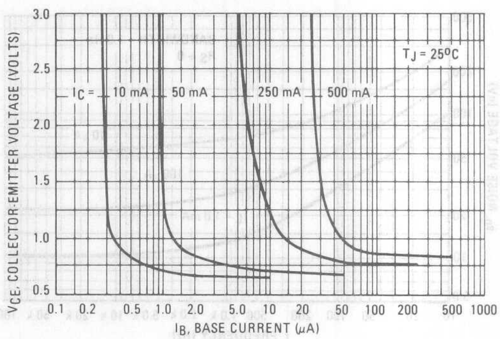


FIGURE 10 – "ON" VOLTAGES

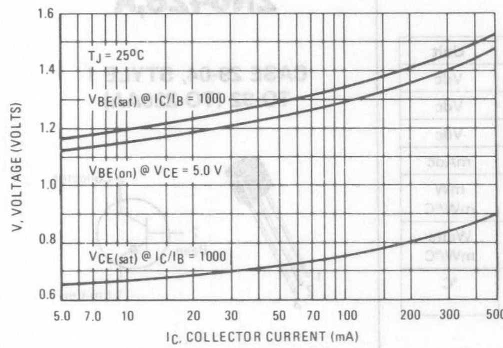


FIGURE 11 – TEMPERATURE COEFFICIENTS

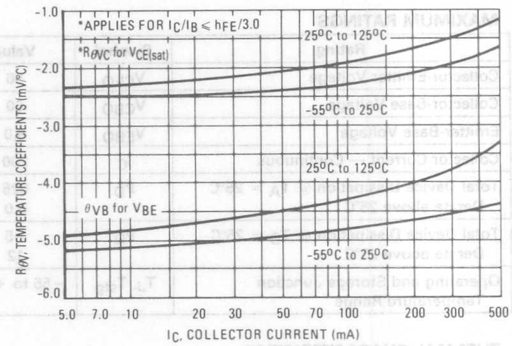


FIGURE 12 – THERMAL RESPONSE

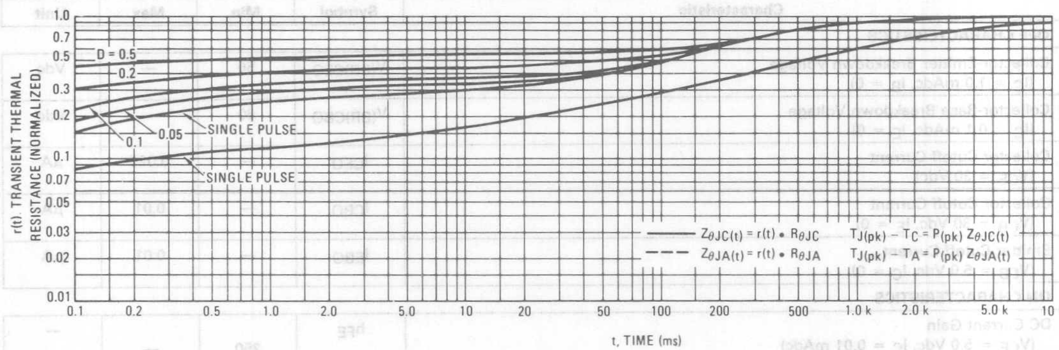
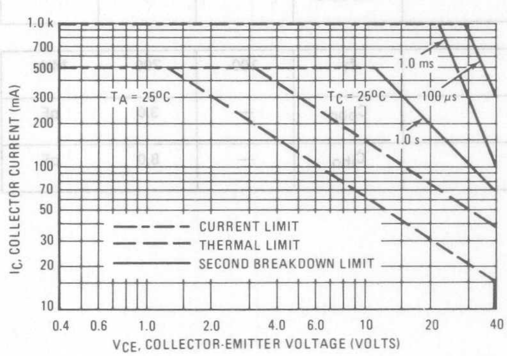
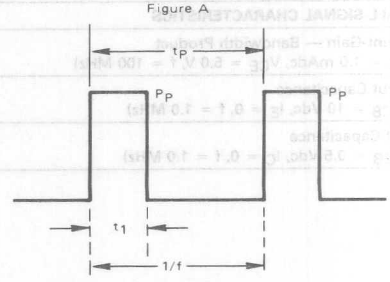


FIGURE 13 – ACTIVE REGION SAFE OPERATING AREA



DESIGN NOTE: USE OF TRANSIENT THERMAL RESISTANCE DATA

Figure A



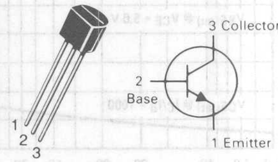
Duty Cycle $= t_1 f = \frac{t_1}{t_P}$

Peak Pulse Power $= P_P$

2

2N6428,A

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	50	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.1$ mAdc, $I_E = 0$)	$V_{(BR)CBO}$	60	—	Vdc
Collector Cutoff Current ($V_{CE} = 30$ Vdc)	I_{CEO}	—	0.025	μA
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	0.01	μA
Emitter Cutoff Current ($V_{EB} = 5.0$ Vdc, $I_C = 0$)	I_{EBO}	—	0.01	μA
ON CHARACTERISTICS				
DC Current Gain ($V_{CE} = 5.0$ Vdc, $I_C = 0.01$ mAdc) ($V_{CE} = 5.0$ Vdc, $I_C = 0.1$ mAdc) ($V_{CE} = 5.0$ Vdc, $I_C = 1.0$ mAdc) ($V_{CE} = 5.0$ Vdc, $I_C = 10$ mAdc)	h_{FE}	 250 250 250 250	 — 650 — —	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 0.5$ mAdc) ($I_C = 100$ mAdc, $I_B = 5.0$ mAdc)	$V_{CE(sat)}$	 — —	 0.2 0.6	Vdc
Base-Emitter On Voltage ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc)	$V_{BE(on)}$	0.56	0.66	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ V, f = 100 MHz)	f_T	100	700	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{obo}	—	3.0	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)	C_{ibo}	—	8.0	pF

Input Impedance (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{ie}	3.0	30	kΩ
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{re}	2.0	20	$X\ 10^{-4}$
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{fe}	200	800	—
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{oe}	5.0	50	μmhos

NOISE FIGURE/TOTAL NOISE VOLTAGE CHARACTERISTICS

		NF Max (1)	V_T Max (1)	NF Max (2)	V_T Max (2)	NF Max (3)	V_T Max (3)	Unit	Unit
Noise Figure/Voltage (V_{CE} = 5.0 V, I_C = 0.1 mA, T_A = 25°C)	2N6428	3.0	18.1	6.0	5700	3.5	4.3	dB	nV
	2N6428A	2.0	16.2	4.0	4600	3.0	4.1	dB	nV

(1) R_S = 10 kΩ, BW = 1.0 Hz, f = 100 Hz
(2) R_S = 50 kΩ, BW = 15.7 kHz, f = 10 Hz–10 kHz
(3) R_S = 500 Ω, BW = 1.0 Hz, f = 10 Hz

2

MAXIMUM RATINGS

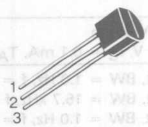
Rating	Symbol	2N6515	2N6516 2N6519	2N6517 2N6520	Unit
Collector-Emitter Voltage	V_{CEO}	250	300	350	Vdc
Collector-Base Voltage	V_{CBO}	250	300	350	Vdc
Emitter-Base Voltage 2N6515, 2N6516, 2N6517 2N6519, 2N6520	V_{EBO}		 6.0 5.0		Vdc
Base Current	I_B		250		mAdc
Collector Current — Continuous	I_C		500		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D		0.625 5.0		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−55 to +150		°C
Lead Temperature ≥1/16″ from case for 10 seconds	T_L		260		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

NPN
2N6515
thru 2N6517
PNP
2N6519
2N6520

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



HIGH VOLTAGE TRANSISTORS

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1)		$V_{(BR)CEO}$			Vdc
($I_C = 1.0$ mAdc, $I_B = 0$)	2N6515		250	—	
	2N6516, 2N6519		300	—	
	2N6517, 2N6520		350	—	
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$			Vdc
($I_C = 100$ μAdc, $I_E = 0$)	2N6515		250	—	
	2N6516, 2N6519		300	—	
	2N6517, 2N6520		350	—	
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$			Vdc
($I_E = 10$ μAdc, $I_C = 0$)	2N6515, 2N6516, 2N6517		6.0	—	
	2N6519, 2N6520		5.0	—	
Collector Cutoff Current		I_{CBO}			nAdc
($V_{CB} = 150$ Vdc, $I_E = 0$)	2N6515		—	50	
($V_{CB} = 200$ Vdc, $I_E = 0$)	2N6516, 2N6519		—	50	
($V_{CB} = 250$ Vdc, $I_E = 0$)	2N6517, 2N6520		—	50	
Emitter Cutoff Current		I_{EBO}			nAdc
($V_{EB} = 5.0$ Vdc, $I_C = 0$)	2N6515, 2N6516, 2N6517		—	50	
($V_{EB} = 4.0$ Vdc, $I_C = 0$)	2N6519, 2N6520		—	50	
ON CHARACTERISTICS(1)					
DC Current Gain		h_{FE}			—
($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc)	2N6515		35	—	
	2N6516, 2N6519		30	—	
	2N6517, 2N6520		20	—	
($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc)	2N6515		50	—	
	2N6516, 2N6519		45	—	
	2N6517, 2N6520		30	—	
($I_C = 30$ mAdc, $V_{CE} = 10$ Vdc)	2N6515		50	300	
	2N6516, 2N6519		45	270	
	2N6517, 2N6520		30	200	
($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc)	2N6515		45	220	
	2N6516, 2N6519		40	200	
	2N6517, 2N6520		20	200	
($I_C = 100$ mAdc, $V_{CE} = 10$ Vdc)	2N6515		25	—	
	2N6516, 2N6519		20	—	
	2N6517, 2N6520		15	—	

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)		—	0.30	
(I_C = 20 mAdc, I_B = 2.0 mAdc)		—	0.35	
(I_C = 30 mAdc, I_B = 3.0 mAdc)		—	0.50	
(I_C = 50 mAdc, I_B = 5.0 mAdc)		—	1.0	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)		—	0.75	
(I_C = 20 mAdc, I_B = 2.0 mAdc)		—	0.85	
(I_C = 30 mAdc, I_B = 3.0 mAdc)		—	0.90	
Base-Emitter On Voltage (I_C = 100 mAdc, V_{CE} = 10 Vdc)	$V_{BE(on)}$	—	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product(1) (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 20 MHz)	f_T	40	200	MHz
Collector-Base Capacitance (V_{CB} = 20 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	—	6.0	pF
Emitter-Base Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{eb}			pF
2N6515 thru 2N6517		—	80	
2N6519, 2N6520		—	100	
SWITCHING CHARACTERISTICS				
Turn-On Time (V_{CC} = 100 Vdc, $V_{BE(off)}$ = 2.0 Vdc, I_C = 50 mAdc, I_{B1} = 10 mAdc)	t_{on}	—	200	ns
Turn-Off Time (V_{CC} = 100 Vdc, I_C = 50 mAdc, I_{B1} = I_{B2} = 10 mAdc)	t_{off}	—	3.5	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

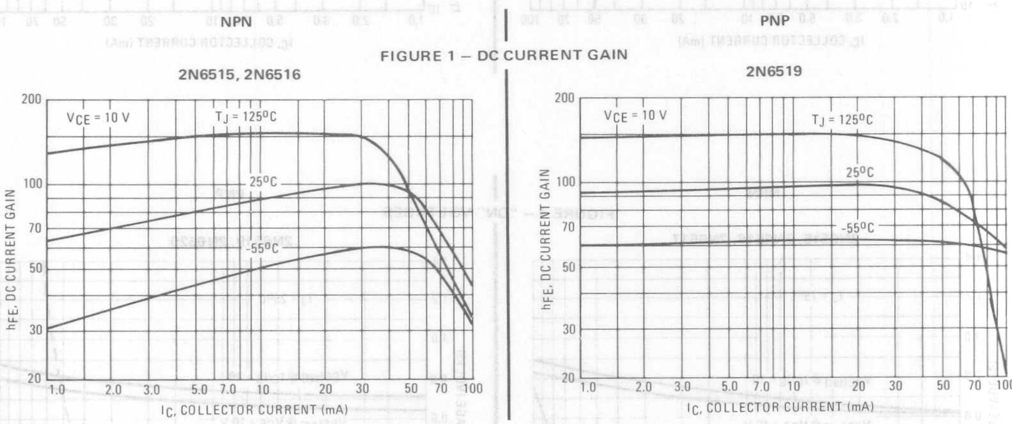


FIGURE 1 — DC CURRENT GAIN

FIGURE 2 — DC CURRENT GAIN

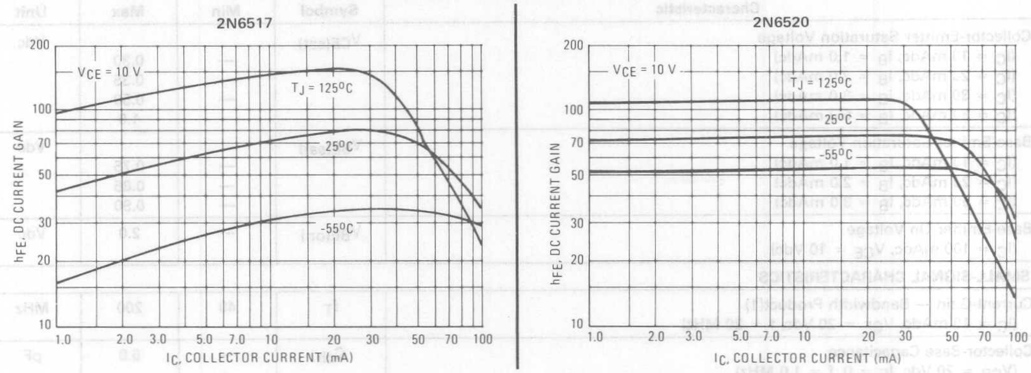


FIGURE 3 — CURRENT-GAIN — BANDWIDTH PRODUCT

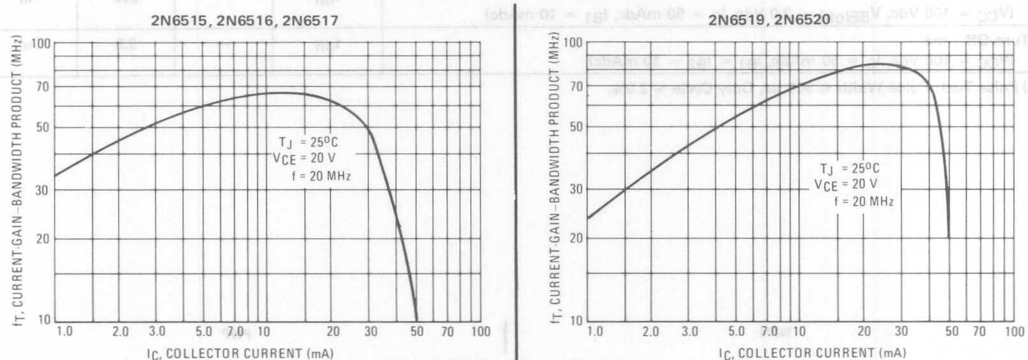


FIGURE 4 — "ON" VOLTAGES

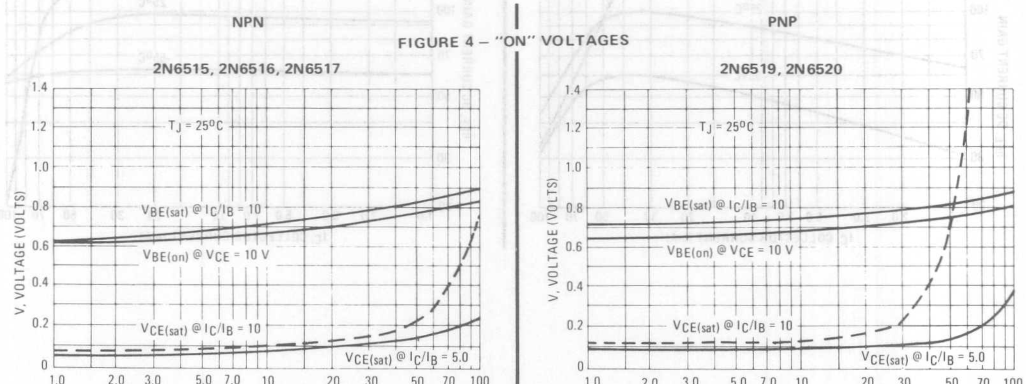
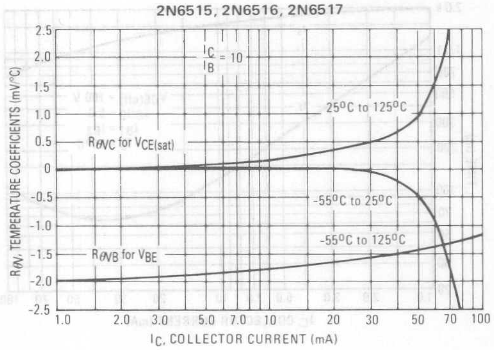


FIGURE 5 – TEMPERATURE COEFFICIENTS

2N6515, 2N6516, 2N6517



2N6519, 2N6520

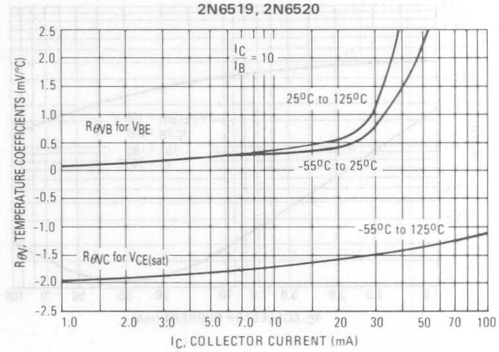
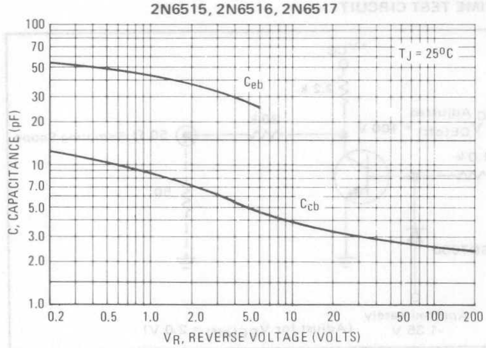
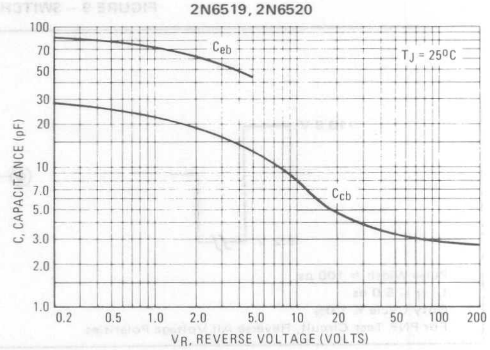


FIGURE 6 – CAPACITANCE

2N6515, 2N6516, 2N6517



2N6519, 2N6520

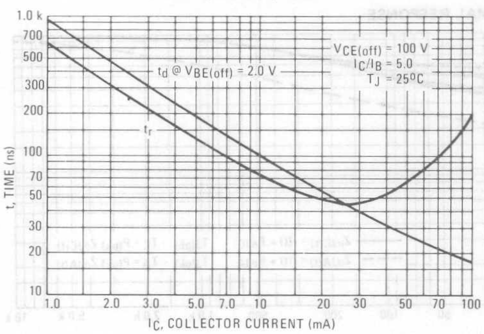


NPN

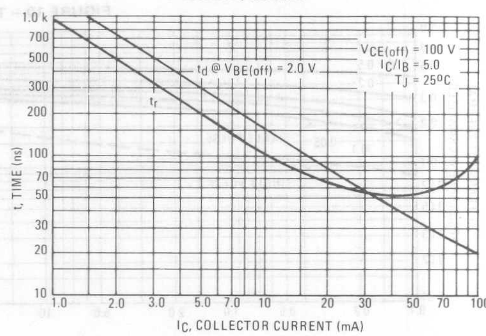
PNP

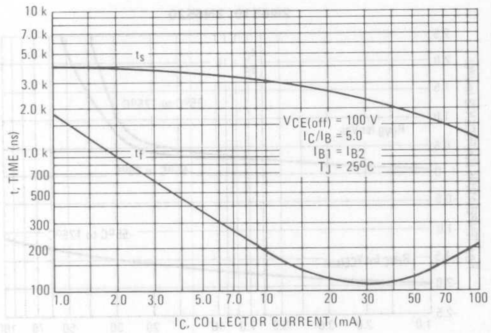
FIGURE 7 – TURN-ON TIME

2N6515, 2N6516, 2N6517



2N6519, 2N6520





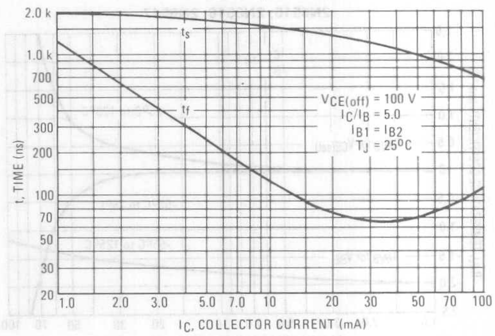


FIGURE 9 – SWITCHING TIME TEST CIRCUIT

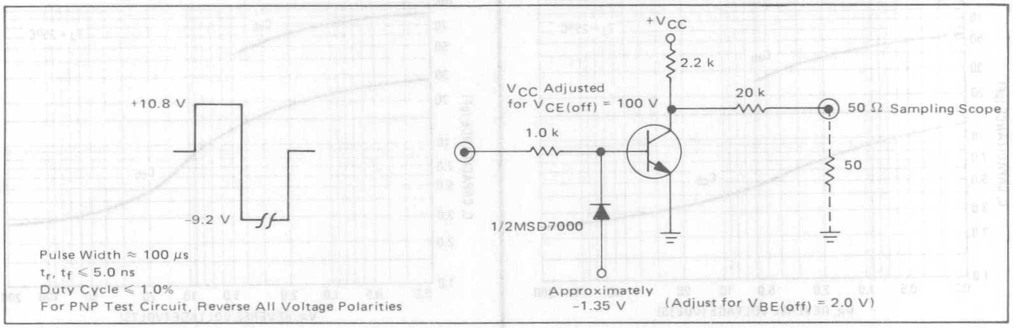


FIGURE 10 – THERMAL RESPONSE

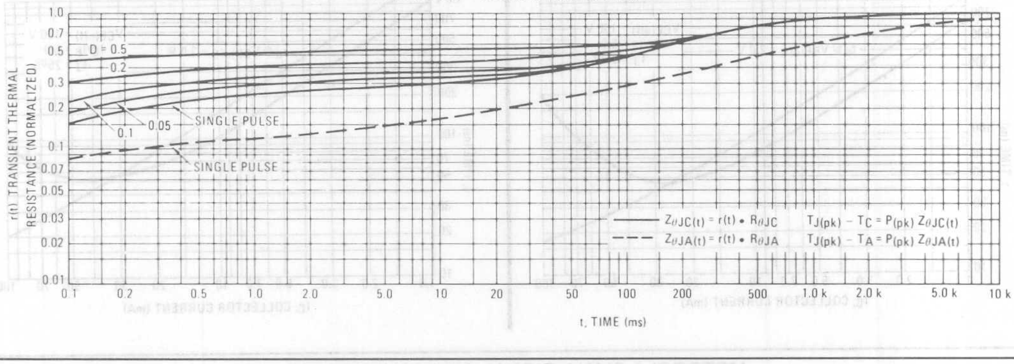
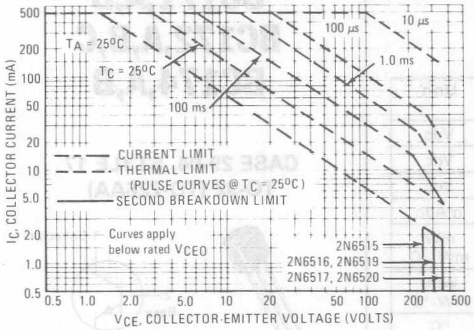
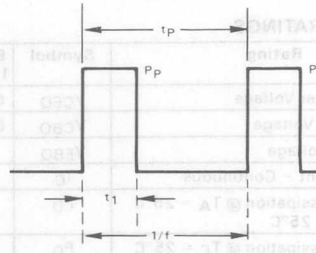


FIGURE 11 – ACTIVE REGION SAFE OPERATING AREA



DESIGN NOTE: USE OF TRANSIENT THERMAL RESISTANCE DATA

Figure A

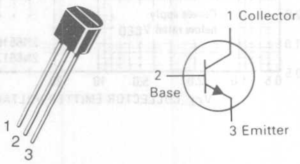


Duty Cycle = $t_1 f = \frac{t_1}{t_P}$

Peak Pulse Power = P_P

BC171,A,B
BC172,A,B,C
BC174,A,B

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

NPN SILICON

Refer to BC546 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BC 174	BC 171	BC 172	Unit
Collector-Emitter Voltage	V_{CEO}	65	45	25	Vdc
Collector-Base Voltage	V_{CBO}	80	50	30	Vdc
Emitter-Base Voltage	V_{EBO}		6.0		Vdc
Collector Current – Continuous	I_C		100		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D		350 2.8		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D		1.0 8.0		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		–55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	357	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

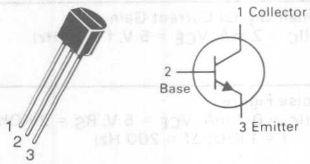
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage ($I_C = 2.0$ mA, $I_B = 0$)	BC174 BC171 BC172	$V_{(BR)CEO}$	65 45 25	— — —	— — —	V
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu A$, $I_C = 0$)	BC171 BC172 BC174	$V_{(BR)EBO}$	6.0 6.0 6.0	— — —	— — —	V
Collector Cutoff Current ($V_{CE} = 70$ V, $V_{BE} = 0$) ($V_{CE} = 50$ V, $V_{BE} = 0$) ($V_{CE} = 35$ V, $V_{BE} = 0$) ($V_{CE} = 30$ V, $V_{BE} = 0$) $T_A = 125°C$	BC174 BC171 BC172	I_{CES}	— — — —	0.2 0.2 0.2 —	15 15 15 4.0	nA μA
ON CHARACTERISTICS						
DC Current Gain ($I_C = 10\ \mu A$, $V_{CE} = 5.0$ V)	BC171A/2A/4A BC171B/2B/4B BC172C	h_{FE}	— — —	90 150 270	— — —	
($I_C = 2.0$ mA, $V_{CE} = 5.0$ V)	BC174 BC171 BC172 BC171A/2A/4A BC171B/2B/4B BC172C		120 120 120 120 180 380	— — — 180 290 520	450 800 800 220 460 800	
($I_C = 100$ mA, $V_{CE} = 5.0$ V)	BC171A/2A/4A BC171B/2B/4B BC172C		— — —	120 180 300	— — —	
Collector-Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 0.5$ mA) ($I_C = 100$ mA, $I_B = 5.0$ mA)		$V_{CE(sat)}$	 — —	 0.09 0.2	 0.25 0.6	V
Base-Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 0.5$ mA)		$V_{BE(sat)}$	—	0.7	—	V
Base-Emitter On Voltage ($I_C = 2.0$ mA, $V_{CE} = 5.0$ V)		$V_{BE(on)}$	0.55	—	0.7	V

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted)

Characteristic	Type	Symbol	Min.	Typ.	Max.	Unit
DYNAMIC CHARACTERISTICS, SMALL SIGNAL CHARACTERISTICS						
Current-Gain Bandwidth Product (I_C = 10 mA, V_{CE} = 5 V, f = 100 MHz)	BC171 BC172 BC174	f_T	150 150 150	300 300 300		MHz
Output Capacitance (V_{CB} = 10 V, I_C = 0, f = 1 MHz)		C_{obo}		1.7	4.5	pF
Input Capacitance (V_{BE} = 0.5 V, I_C = 0, f = 1 MHz)		C_{ibo}		10		pF
Small-Signal Current Gain (I_C = 2 mA, V_{CE} = 5 V, f = 1 KHz)	BC171/172/174 BC171A/2A/4A BC171B/2B/4B BC172C	h_{fe}	125 125 240 450	— 220 330 600	900 260 500 900	
Noise Figure (I_C = 0.2 mA, V_{CE} = 5 V, R_S = 2 KOhms, f = 1 KHz, Δf = 200 Hz)	BC171 BC172 BC174	NF		2 2 2	10 10 10	dB

BC183,A,B,C
BC184,B,C

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

NPN SILICON

Refer to BC237 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BC 182	BC 183	BC 184	Unit
Collector-Emitter Voltage	V_{CEO}	50	30	30	Vdc
Collector-Base Voltage	V_{CBO}	60	45	45	Vdc
Emitter-Base Voltage	V_{EBO}		6.0		Vdc
Collector Current − Continuous	I_C		100		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D		350 2.8		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D		1.0 8.0		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

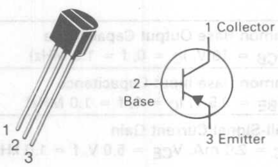
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 2.0 mA, I_B = 0)	BC182 BC183 BC184	$V_{(BR)CEO}$	50 30 30	— — —	— — —	V
Collector-Base Breakdown Voltage (I_C = 10 μA, I_E = 0)	BC182 BC183 BC184	$V_{(BR)CBO}$	60 45 45	— — —	— — —	V
Emitter-Base Breakdown Voltage (I_E = 100 μA, I_C = 0)		$V_{(BR)EBO}$	6.0	—	—	V
Collector Cutoff Current (V_{CB} = 50 V, V_{BE} = 0) (V_{CB} = 30 V, V_{BE} = 0)	BC182 BC183 BC184	I_{CBO}	— — —	0.2 0.2 0.2	15 15 15	nA
Emitter-Base Leakage Current (V_{EB} = 4.0 V, I_C = 0)		I_{EBO}	—	—	15	nA
ON CHARACTERISTICS						
DC Current Gain (I_C = 10 μA, V_{CE} = 5.0 V)	BC182 BC183 BC184	h_{FE}	40 40 100	— — —	— — —	
(I_C = 2.0 mA, V_{CE} = 5.0 V)	BC182 BC183 BC184		120 120 250	— — —	500 800 800	
(I_C = 100 mA, V_{CE} = 5.0 V)	BC182 BC183 BC184		80 80 130	— — —	— — —	
Collector-Emitter On Voltage	(I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)*	$V_{CE(sat)}$	— —	0.07 0.2	0.25 0.6	V
Base-Emitter Saturation Voltage	(I_C = 100 mA, I_B = 5.0 mA)*	$V_{BE(sat)}$	—	—	1.2	V
Base-Emitter On Voltage	(I_C = 100 μA, V_{CE} = 5.0 V) (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 100 mA, V_{CE} = 5.0 V)*	$V_{BE(on)}$	— 0.55 —	0.5 0.62 0.83	— 0.7 —	V

*Pulse Test: Tp 300 s, Duty Cycle 2.0%.

Characteristic		Symbol	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS						
Current-Gain Bandwidth Product		f_T				MHz
(I_C = 0.5 mA, V_{CE} = 3.0 V, f = 100 MHz)	BC182		—	100	—	
	BC183		—	120	—	
	BC184		—	140	—	
(I_C = 10 mA, V_{CE} = 5.0 V, f = 100 MHz)	BC182		150	200	—	
	BC183		150	240	—	
	BC184		150	280	—	
Common Base Output Capacitance (V_{CB} = 10 V, I_C = 0, f = 1.0 MHz)		C_{ob}	—	—	5.0	pF
Common Base Input Capacitance (V_{BE} = 0.5 V, I_C = 0, f = 1.0 MHz)		C_{ib}	—	8.0	—	pF
Small-Signal Current Gain		h_{fe}				
(I_C = 2.0 mA, V_{CE} = 5.0 V, f = 1.0 kHz)	BC182		125		500	
	BC183		125		900	
	BC184		240	—	900	
	BC182A, BC183A		125		260	
	BC182B, BC183B, BC184B		240	—	500	
	BC183C, BC184C		450	—	900	
Noise Figure		NF				dB
(I_C = 0.2 mA, V_{CE} = 5.0 V, R_S = 2.0 kohms, f = 30 Hz to 15 kHz)	BC184		—	2.0	4.0	
(I_C = 0.2 mA, V_{CE} = 5.0 V, R_S = 2.0 kohms, f = 1.0 kHz, F = 200 Hz)	BC182		—	2.0	10	
	BC183		—	2.0	10	
	BC184		—	2.0	4.0	

BC212,A,B
BC213,A,B,C
BC214,B,C

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

PNP SILICON

Refer to BC307 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BC 212	BC 213	BC 214	Unit
Collector-Emitter Voltage	V_{CEO}	50	30	30	Vdc
Collector-Base Voltage	V_{CBO}	60	45	45	Vdc
Emitter-Base Voltage	V_{EBO}	5.0			Vdc
Collector Current − Continuous	I_C	100			mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8			mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0			Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Type	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 2.0 mAdc, I_B = 0)	BC212 BC213 BC214	$V_{(BR)CEO}$	50 30 30	— — —	— — —	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μA, I_E = 0)	BC212 BC213 BC214	$V_{(BR)CBO}$	60 45 45	— — —	— — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	BC212 BC213 BC214	$V_{(BR)EBO}$	5 5 5	— — —	— — —	Vdc
Collector-Emitter Leakage Current (V_{CB} = 30 V)	BC212 BC213 BC214	I_{CBO}	— — —	— — —	15 15 15	nAdc
Emitter-Base Leakage Current (V_{EB} = 4 V, I_C = 0)	BC212 BC213 BC214	I_{EBO}	— — —	— — —	15 15 15	nAdc
ON CHARACTERISTICS						
DC Current Gain (I_C = 10 μAdc, V_{CE} = 5 Vdc)	BC212 BC213 BC214	h_{FE}	40 40 100	— — —	— — —	
(I_C = 2 mAdc, V_{CE} = 5 Vdc)	BC212 BC213 BC214		60 80 140	— — —	— — 600	
(I_C = 100 mAdc, V_{CE} = 5 Vdc)*	BC212, BC214 BC213		— —	120 140	— —	

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted)

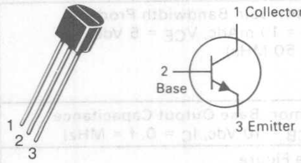
Characteristic	Type	Symbol	Min	Typ	Max	Unit
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$				Vdc
(I_C = 10 mAdc, I_B = 0.5 mAdc)			—	0.10	—	
(I_C = 100 mAdc, I_B = 5 mAdc)*			—	0.25	0.6	
Base-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 5 mAdc)		$V_{BE(sat)}$	—	1.00	1.4	Vdc
Base-Emitter on Voltage (I_C = 2 mAdc, V_{CE} = 5 Vdc)		$V_{BE(on)}$	0.6	0.62	0.72	Vdc
DYNAMIC CHARACTERISTICS						
Current-Gain Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5 Vdc, f = 50 MHz)		f_T				MHz
	BC212		—	280	—	
	BC214		—	320	—	
	BC213		—	360	—	
Common-Base Output Capacitance (V_{CB} = 10 Vdc, I_C = 0, f = MHz)		C_{ob}	—	—	6.0	pF
Noise Figure		NF				dB
(I_C = 0.2 mAdc, V_{CE} = 5 Vdc, R_S = 2 Kohms, f = 30 Hz to 15 KHz)	BC214		—	—	2	
(I_C = 0.2 mAdc, V_{CE} = 5 Vdc, R_S = 2 Kohms, f = 1 KHz, f = 200 Hz)	BC213		—	—	10	
	BC212		—	—	10	
Small Signal Current Gain (I_C = 2 mAdc, V_{CE} = 5 Vdc, f = 1 KHz)		h_{fe}				
	BC212		60	—	—	
	BC213		80	—	—	
	BC214		140	—	—	
	BC212A, BC213A		100	—	300	
	BC212B, BC213B,		200	—	400	
	BC214B		200	—	400	
	BC213C, BC214C		350	—	600	

*Pulse-test: Tp 300 s, Duty-cycle 2%.

2

BC238,A,B,C
BC239,B,C

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	BC 237	BC 238	BC 239	Unit
Collector-Emitter Voltage	V_{CEO}	45	25	25	Vdc
Collector-Emitter Voltage	V_{CES}	50	30	30	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	5.0	5.0	Vdc
Collector Current — Continuous	I_C	100			mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8			mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0			Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Type	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 2.0 mA, I_B = 0)	BC237 BC238 BC239	$V_{(BR)CEO}$	45 25 25			V
Emitter-Base Breakdown Voltage (I_E = 100 μA, I_C = 0)	BC237 BC238 BC239	$V_{(BR)EBO}$	6 5 5			V
Collector Cutoff Current (V_{CE} = 30 V, V_{BE} = 0) (V_{CE} = 50 V, V_{BE} = 0)	BC238 BC239 BC237	I_{CES}		0.20 0.20 0.20	15 15 15	nA
(V_{CE} = 30 V, V_{BE} = 0) T_A = 125°C (V_{CE} = 50 V, V_{BE} = 0) T_A = 125°C	BC238 BC239 BC237			0.20 0.20 0.20	4 4 4	μA
ON CHARACTERISTICS						
DC Current Gain (I_C = 10 μA, V_{CE} = 5 V)	BC237A/238A BC237B/238B/239B BC237C/238C/239C	h_{FE}		90 150 270		
(I_C = 2 mA, V_{CE} = 5 V)	BC237 BC238 BC239 BC237A/238A BC237B/238B/239B BC237C/238C/239C		120 120 120 120 200 380	 170 290 500	800 800 800 220 460 800	
(I_C = 100 mA, V_{CE} = 5 V)	BC237A/238A BC237B/238B/239B BC237C/238C/239C			120 180 300		
Collector-Emitter On Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5 mA)	BC237/BC238/BC239 BC237/BC239 BC238	$V_{CE(sat)}$		0.07 0.20	0.20 0.60 0.8	V
Base-Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5 mA)		$V_{BE(sat)}$		0.60	0.83 1.05	V
Base-Emitter On Voltage (I_C = 100 μA, V_{CE} = 5 V) (I_C = 2 mA, V_{CE} = 5 V) (I_C = 100 mA, V_{CE} = 5 V)		$V_{BE(on)}$	 0.55	0.50 0.62 0.83	 0.70	V

Characteristic	Type	Symbol	Min.	Typ.	Max.	Unit
DYNAMIC CHARACTERISTICS						
Current-Gain Bandwidth Product		f_T				MHz
(I_C = 0.5 mA, V_{CE} = 3 V, f = 100 MHz)	BC237			100		
	BC238			120		
	BC239			140		
(I_C = 10 mA, V_{CE} = 5 V, f = 100 MHz)	BC237		150	200		
	BC238		150	240		
	BC239		150	280		
Collector-Base Capacitance (V_{CB} = 10 V, I_C = 0, f = 1 MHz)		C_{obo}			4.50	pF
Emitter-Base Capacitance (V_{BE} = 0.5 V, I_C = 0, f = 1 MHz)		C_{ibo}		8.0		pF
Noise Figure		NF				dB
(I_C = 0.2 mA, V_{CE} = 5 V, R_S = 2 Kohms, f = 30 Hz to 15 KHz)	BC239			2	4	
(I_C = 0.2 mA, V_{CE} = 5 V, R_S = 2 Kohms, f = 1 KHz, Δf = 200 Hz)	BC237			2	10	
	BC238			2	10	
	BC239			2	4	

FIGURE 1 – NORMALIZED DC CURRENT GAIN

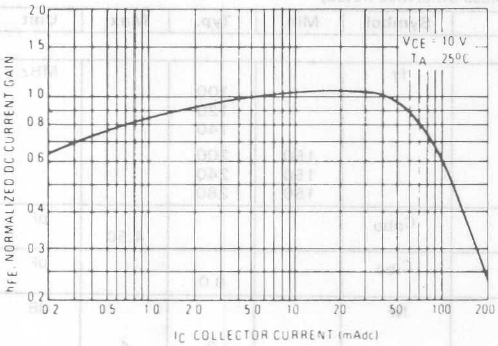


FIGURE 2 – "SATURATION" AND "ON" VOLTAGES

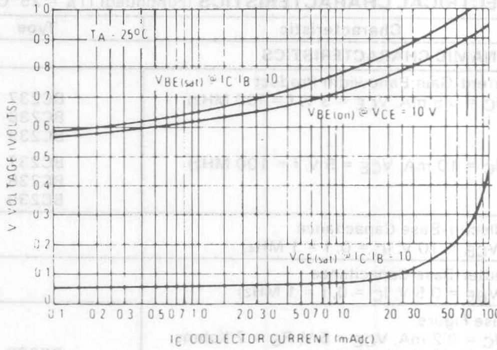


FIGURE 3 – CURRENT GAIN-BANDWIDTH PRODUCT

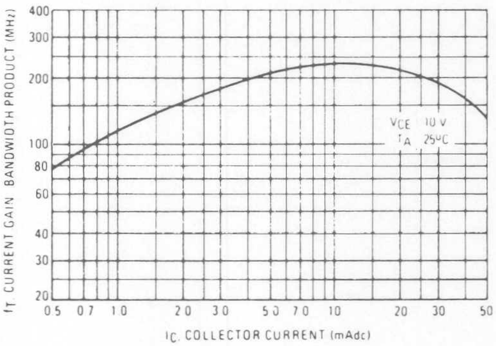


FIGURE 4 – CAPACITANCES

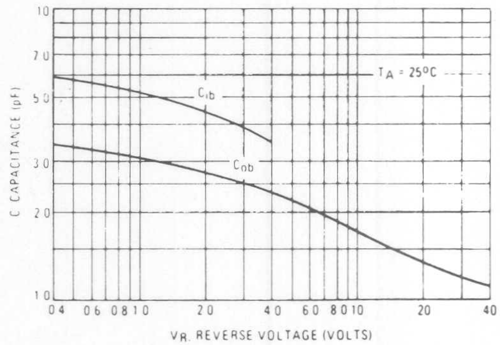
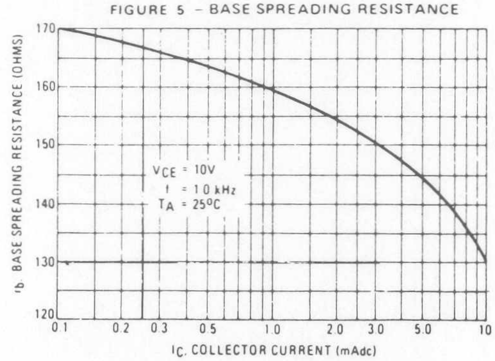
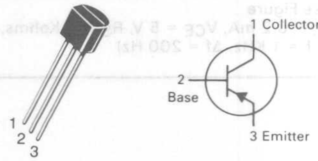


FIGURE 5 – BASE SPREADING RESISTANCE



BC251,A,B,C
BC252,A,B,C
BC256,A,B

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

PNP SILICON

Refer to BC556 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BC 256	BC 251	BC 252	Unit
Collector-Emitter Voltage	V_{CEO}	65	45	25	Vdc
Collector-Base Voltage	V_{CBO}	80	50	30	Vdc
Emitter-Base Voltage	V_{EBO}		5.0		Vdc
Collector Current − Continuous	I_C		100		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D		350 2.8		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D		1.0 8.0		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	357	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted)

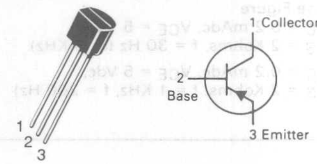
Characteristic	Type	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage ($I_C = 2.0$ mA, $I_B = 0$)	BC256 BC251 BC252	$V_{(BR)CEO}$	65 45 25			V
Emitter-Base Breakdown Voltage ($I_E = 100$ µA, $I_C = 0$)	BC256 BC251 BC252	$V_{(BR)EBO}$	5 5 5			V
Collector-Emitter Leakage Current ($V_{CES} = 40$ V) ($V_{CES} = 20$ V)	BC256 BC251 BC252	I_{CES}		2 2 2	100 100 100	nA
($V_{CES} = 20$ V, $T_A = 125°C$)	BC256 BC251 BC252				4 4 4	µA
ON CHARACTERISTICS						
DC Current Gain ($I_C = 10$ µA, $V_{CE} = 5$ V)	BC251A/2A/6A BC251B/2B/6B BC252C	h_{FE}		90 150 270		
($I_C = 2$ mA, $V_{CE} = 5$ V)	BC256 BC251 BC252 BC251A/2A/6A BC251B/2B/6B BC251C/BC252C		125 120 120 120 180 380	 170 290 500	500 800 800 220 460 800	
($I_C = 100$ mA, $V_{CE} = 5$ V)	BC251A/2A/6A BC251B/2B/6B BC252C			120 180 300		
Collector-Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 0.5$ mA) ($I_C = 100$ mA, $I_B = 5$ mA)		$V_{CE(sat)}$		0.075 0.25	0.3 0.65	V
Base-Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 0.5$ mA) ($I_C = 100$ mA, $I_B = 5$ mA)		$V_{BE(sat)}$		0.70 1.00		V
Base-Emitter on Voltage ($I_C = 2$ mA, $V_{CE} = 5$ V)		$V_{BE(on)}$	0.55	0.62	0.70	V

Characteristic	Type	Symbol	Min.	Typ.	Max.	Unit
DYNAMIC CHARACTERISTICS						
Current-Gain Bandwidth Product (I_C = 10 mA, V_{CE} = 5 V, f = 50 MHz)	BC256 BC251 BC252	f_T		280 320 360		MHz
Output Capacitance (V_{CB} = 10 V, I_C = 0, f = 1 MHz)		C_{ob}		3	6.0	pF
Noise Figure (I_C = 0.2 mA, V_{CE} = 5 V, R_S = 2 Kohms, f = 1 KHz, Δf = 200 Hz)	BC256 BC251 BC252	NF		2 2 2	10 10 10	dB

BC308,A,B,C
BC309,A,B,C

2

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	BC 307	BC 308	BC 309	Unit
Collector-Emitter Voltage	V_{CEO}	45	25	25	Vdc
Collector-Base Voltage	V_{CBO}	50	30	30	Vdc
Emitter-Base Voltage	V_{EBO}		5.0		Vdc
Collector Current – Continuous	I_C		100		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D		350 2.8		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D		1.0 8.0		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Type	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage	BC307	$V_{(BR)CEO}$	45	—	—	Vdc
(I_C = 2.0 mAdc, I_B = 0)	BC308		25	—	—	
	BC309		25	—	—	
Emitter-Base Breakdown Voltage	BC307	$V_{(BR)EBO}$	5	—	—	Vdc
(I_E = 100 μAdc, I_C = 0)	BC308		5	—	—	Vdc
	BC309		5	—	—	
Collector-Emitter Leakage Current		I_{CES}				nA
(V_{CES} = 50 V, V_{BE} = 0)	BC307			0.2	15	
(V_{CES} = 30 V, V_{BE} = 0)	BC308			0.2	15	
	BC309			0.2	15	
(V_{CES} = 50 V, V_{BE} = 0) T_A = 125°C	BC307			0.2	4.0	μA
(V_{CES} = 30 V, V_{BE} = 0) T_A = 125°C	BC308			0.2	4.0	
	BC309			0.2	4.0	
ON CHARACTERISTICS						
DC Current Gain		h_{FE}				
(I_C = 10 μAdc, V_{CE} = 5 Vdc)	BC307A/308A/309A		—	90	—	
	BC307B/308B/309B		—	150	—	
	BC307C/308C/309C		—	270	—	
(I_C = 2 mAdc, V_{CE} = 5 Vdc)	BC307		120	—	800	
	BC308		120	—	800	
	BC309		120	—	800	
	BC307A/308A/309A		120	170	220	
	BC307B/308B/309B		200	290	460	
	BC307C/308C/309C		420	500	800	
(I_C = 100 mAdc, V_{CE} = 5 Vdc)	BC307A/308A/309A		—	120	—	
	BC307B/308B/309B		—	180	—	
	BC307C/308C/309C		—	300	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$				Vdc
(I_C = 10 mAdc, I_B = 0,5 mAdc)			—	0.10	0.30	
(I_C = 10 mAdc, I_B = see Note 1)			—	0.30	0.60	
(I_C = 100 mAdc, I_B = 5 mAdc)			—	0.25	—	
Base-Emitter Saturation Voltage		$V_{BE(sat)}$				Vdc
(I_C = 10 mAdc, I_B = 0.5 mAdc)			—	0.70	—	
(I_C = 100 mAdc, I_B = 5 mAdc)			—	1.00	—	
Base-Emitter on Voltage		$V_{BE(on)}$				Vdc
(I_C = 2 mAdc, V_{CE} = 5 Vdc)			0.55	0.62	0.70	

Note 1: I_C = 10 mAdc on the constant base current characteristic, which yields the point I_C = 11 mAdc, V_{CE} = 1 V

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted)

Characteristic	Type	Symbol	Min.	Typ.	Max.	Unit
DYNAMIC CHARACTERISTICS						
Current-Gain Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5 Vdc, f = 50 MHz)	BC307	f_T	—	280	—	MHz
	BC308		—	320	—	
	BC309		—	360	—	
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_C = 0, f = 1 MHz)		C_{cbo}	—	—	6.0	pF
Noise Figure (I_C = 0.2 mAdc, V_{CE} = 5 Vdc, R_S = 2 Kohms, f = 30 Hz to 15 KHz)	BC309	NF	—	2	4	dB
(I_C = 0.2 mAdc, V_{CE} = 5 Vdc, R_S = 2 Kohms, f = 1 KHz, f = 200 Hz)	BC307		—	2	10	
	BC308		—	2	10	
	BC309		—	2	4	

FIGURE 1 – NORMALIZED DC CURRENT GAIN

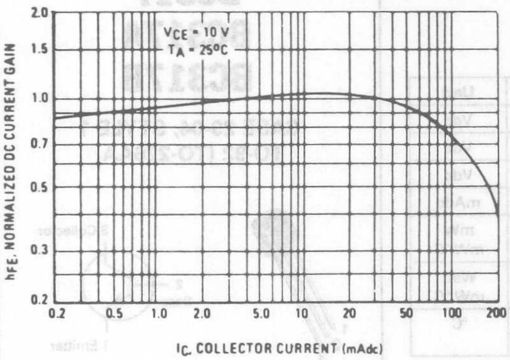


FIGURE 2 – "SATURATION" AND "ON" VOLTAGES

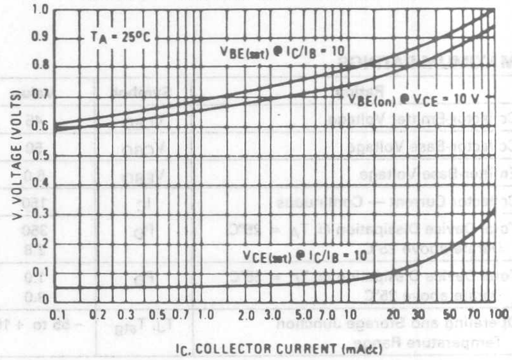


FIGURE 3 – CURRENT-GAIN–BANDWIDTH PRODUCT

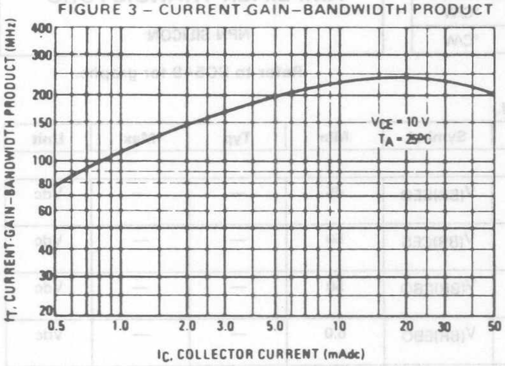


FIGURE 4 – CAPACITANCES

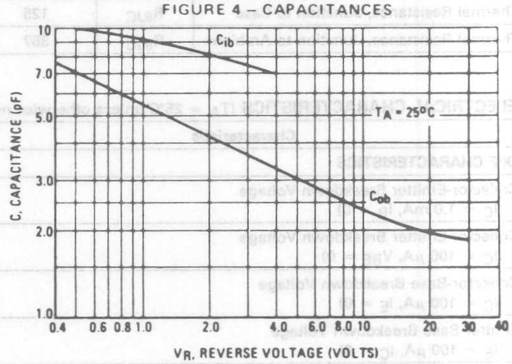


FIGURE 5 – OUTPUT ADMITTANCE

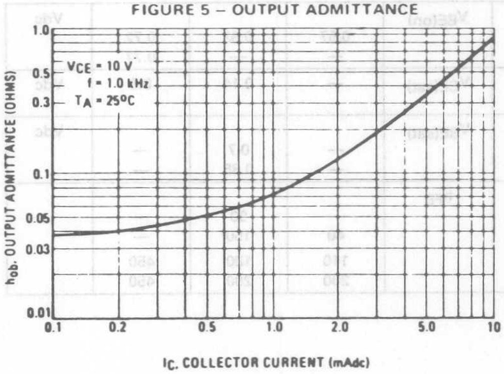
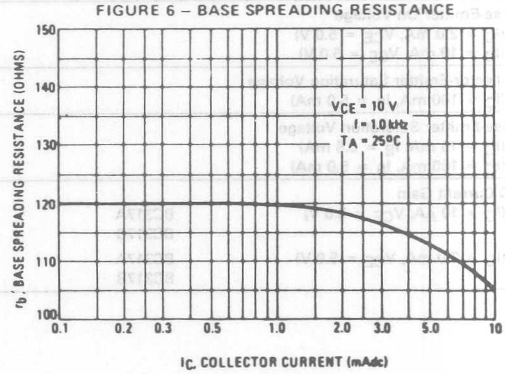
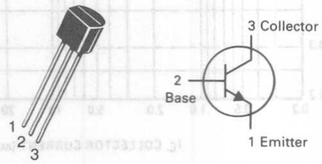


FIGURE 6 – BASE SPREADING RESISTANCE



BC317A
BC317B

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

NPN SILICON

Refer to BC549 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	45	Vdc
Collector-Base Voltage	V_{CBO}	50	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	150	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	357	°C/W

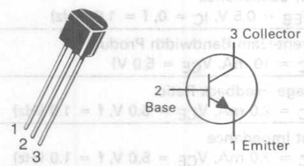
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 1.0 mA, I_B = 0)		$V_{(BR)CEO}$	45	—	—	Vdc
Collector-Emitter Breakdown Voltage (I_C = 100 μA, V_{BE} = 0)		$V_{(BR)CES}$	50	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μA, I_E = 0)		$V_{(BR)CBO}$	50	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μA, I_C = 0)		$V_{(BR)EBO}$	6.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 20 V, I_E = 0)		I_{CBO}	—	—	30	nAdc
ON CHARACTERISTICS						
Base-Emitter On Voltage (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 10 mA, V_{CE} = 5.0 V)		$V_{BE(on)}$	 0.57 —	 0.63 —	 0.72 0.77	Vdc
Collector-Emitter Saturation Voltage (I_C = 100 mA, I_B = 5.0 mA)		$V_{CE(sat)}$	—	0.14	0.6	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)		$V_{BE(sat)}$	 — —	 0.7 0.85	 — —	Vdc
DC Current Gain (I_C = 10 μA, V_{CE} = 5.0 V) (I_C = 2.0 mA, V_{CE} = 5.0 V)	 BC317A BC317B BC317A BC317B	h_{FE}	 — 40 110 200	 90 150 180 290	 — — 450 450	

Characteristic		Symbol	Min	Typ	Max	Unit
SMALL-SIGNAL CHARACTERISTICS						
Spot Noise Figure (I_C = 200 μA, V_{CE} = 5.0 V, R_S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)		NF	—	2.0	6.0	dB
Output Capacitance (V_{CB} = 10 V, I_E = 0, f = 1.0 MHz)		C_{ob}	—	2.5	4.0	pF
Input Capacitance (V_{EB} = 0.5 V, I_C = 0, f = 1.0 MHz)		C_{ib}	—	11.5	—	pF
Current-Gain Bandwidth Product (I_C = 10 mA, V_{CE} = 5.0 V)		f_T	—	280		MHz
Voltage Feedback Ratio (I_C = 2.0 mA, V_{CE} = 5.0 V, f = 1.0 kHz)		h_{re}	—	2.0		$X10^{-4}$
Input Impedance (I_C = 2.0 mA, V_{CE} = 5.0 V, f = 1.0 kHz)		h_{ie}	—	5.0		Kohms
Output Admittance (I_C = 2.0 mA, V_{CE} = 5.0 V, f = 1.0 kHz)		h_{oe}	—	20	—	μmhos
Small-Signal Current Gain (I_C = 2.0 mA, V_{CE} = 5.0 V, f = 1.0 kHz)	BC317A BC317B	h_{fe}	125 240	220 330	260 500	

BC320
BC320A
BC320B

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

NPN SILICON

Refer to BC559 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	45	Vdc
Collector-Base Voltage	V_{CBO}	50	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	150	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

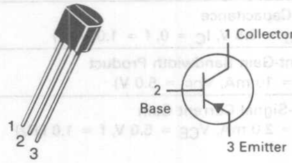
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 1.0 mA, I_B = 0)		$V_{(BR)CEO}$	45	—	—	Vdc
Collector-Emitter Breakdown Voltage (I_C = 100 μA, V_{BE} = 0)		$V_{(BR)CES}$	50	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μA, I_E = 0)		$V_{(BR)CBO}$	50	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μA, I_C = 0)		$V_{(BR)EBO}$	6.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 20 V, I_E = 0)		I_{CBO}	—	—	30	nAdc
ON CHARACTERISTICS						
Base-Emitter On Voltage (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 10 mA, V_{CE} = 5.0 V)		$V_{BE(on)}$	 0.57 —	 0.68 —	 0.72 0.77	Vdc
Collector-Emitter Saturation Voltage (I_C = 100 mA, I_B = 5.0 mA)		$V_{CE(sat)}$	—	0.35	0.5	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)		$V_{BE(sat)}$	 — —	 0.77 0.99	 — —	Vdc
DC Current Gain (I_C = 10 μA, V_{CE} = 5.0 V)	 BC320A BC320B	h_{FE}	 — 40	 50 100	 — —	
(I_C = 2.0 mA, V_{CE} = 5.0 V)	BC320 BC320A BC320B		110 110 200	— — —	450 220 450	

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
SMALL-SIGNAL CHARACTERISTICS						
Spot Noise Figure (I_C = 200 μA, V_{CE} = 5.0 V, R_S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	BC320	NF	—	2.0	6.0	dB
Output Capacitance (V_{CB} = 10 V, I_E = 0, f = 1.0 MHz)		C_{ob}	—	3.0	4.0	pF
Input Capacitance (V_{EB} = 0.5 V, I_C = 0, f = 1.0 MHz)		C_{ib}	—	16	—	pF
Current-Gain Bandwidth Product (I_C = 10 mA, V_{CE} = 5.0 V)		f_T	—	250	—	MHz
Small-Signal Current Gain (I_C = 2.0 mA, V_{CE} = 5.0 V, f = 1.0 kHz)	BC320	h_{fe}	125	—	500	
	BC320A		125	—	260	
	BC320B		240	—	500	

BC328,-16,-25,-40

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	BC327	BC328	Unit
Collector-Emitter Voltage	V_{CEO}	45	25	Vdc
Collector-Base Voltage	V_{CBO}	50	30	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	800		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 10 mA, I_B = 0)	 BC327 BC328	$V_{(BR)CEO}$	 45 25	 — —	 — —	Vdc
Collector-Emitter Breakdown Voltage (I_C = 100 μA, I_E = 0)	 BC327 BC328	$V_{(BR)CES}$	 50 30	 — —	 — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μA, I_C = 0)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 30 V, I_E = 0) (V_{CB} = 20 V, I_E = 0)	 BC327 BC328	I_{CBO}	 — —	 — —	 100 100	nAdc
Collector Cutoff Current (V_{CE} = 45 V, V_{BE} = 0) (V_{CE} = 25 V, V_{BE} = 0)	 BC327 BC328	I_{CES}	 — —	 — —	 100 100	nAdc
Emitter Cutoff Current (V_{EB} = 4.0 V, I_C = 0)		I_{EBO}	—	—	100	nAdc
ON CHARACTERISTICS						
DC Current Gain (I_C = 100 mA, V_{CE} = 1.0 V) (I_C = 300 mA, V_{CE} = 1.0 V)	 BC327/BC328 BC327-16/BC328-16 BC327-25/BC328-25 BC327-40/BC328-40	h_{FE}	 100 100 160 250 40	 — — — — —	 630 250 400 630 —	—
Base-Emitter On Voltage (I_C = 300 mA, V_{CE} = 1.0 V)		$V_{BE(on)}$	—	—	1.2	Vdc
Collector-Emitter Saturation Voltage (I_C = 500 mA, I_B = 50 mA)		$V_{CE(sat)}$	—	—	0.7	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Output Capacitance (V_{CB} = 10 V, I_E = 0, f = 1.0 MHz)		C_{ob}	—	15	—	pF
Current-Gain Bandwidth Product (I_C = 10 mA, V_{CE} = 5.0 V)		f_T	—	260	—	MHz

2

FIGURE 1 – THERMAL RESPONSE

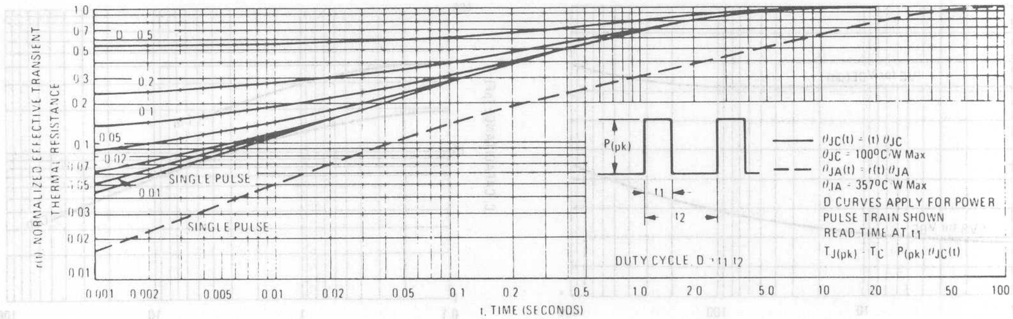


FIGURE 2 – ACTIVE REGION SAFE OPERATING AREA

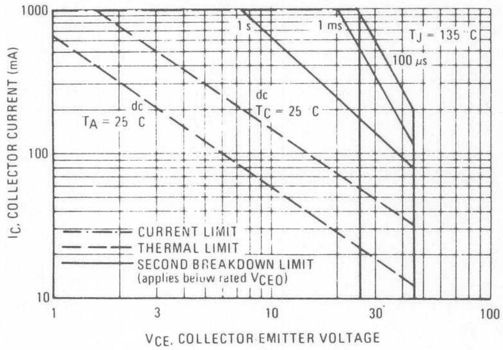


FIGURE 3 – DC CURRENT GAIN

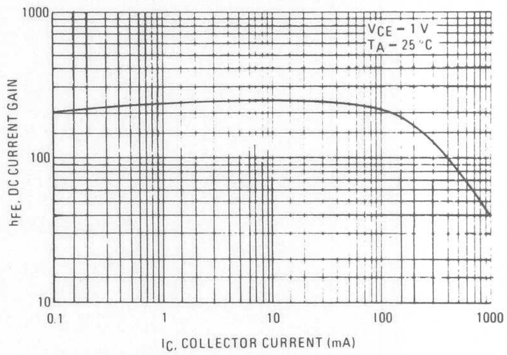


FIGURE 4 – SATURATION REGION

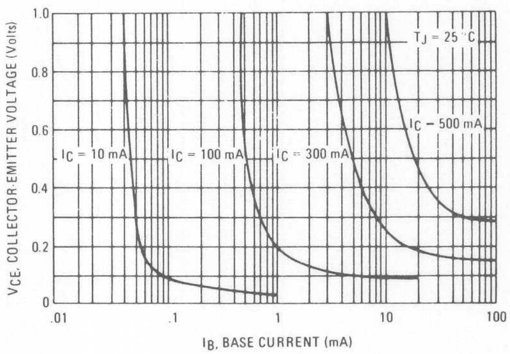


FIGURE 5 – "ON" VOLTAGES

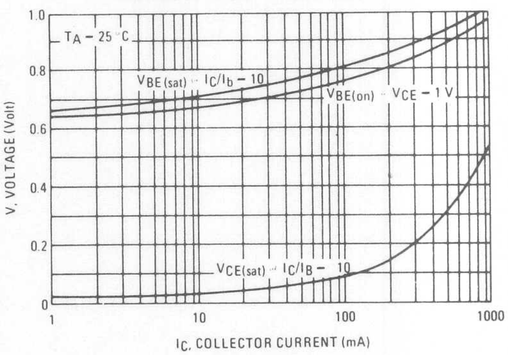


FIGURE 6 – TEMPERATURE COEFFICIENTS

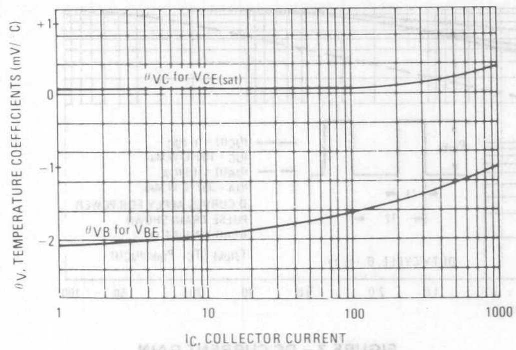
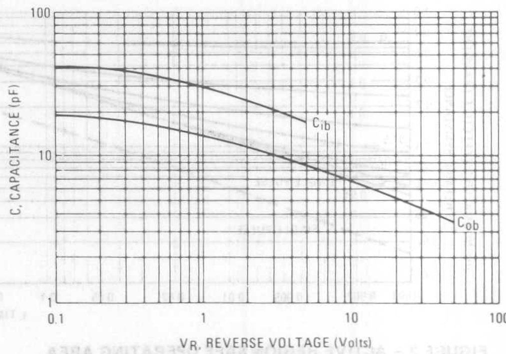


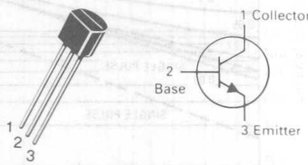
FIGURE 7 – CAPACITANCES



BC337,-16,-25,-40
BC338,-16,-25,-40

2

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	BC337	BC338	Unit
Collector-Emitter Voltage	V_{CEO}	45	25	Vdc
Collector-Base Voltage	V_{CBO}	50	30	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	800		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage ($I_C = 10$ mA, $I_B = 0$)	BC337 BC338	$V_{(BR)CEO}$	45 25	— —	— —	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 100$ μA, $I_E = 0$)	BC337 BC338	$V_{(BR)CES}$	50 30	— —	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μA, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ V, $I_E = 0$) ($V_{CB} = 20$ V, $I_E = 0$)	BC337 BC338	I_{CBO}	—	—	100 100	nAdc
Collector Cutoff Current ($V_{CE} = 45$ V, $V_{BE} = 0$) ($V_{CE} = 25$ V, $V_{BE} = 0$)	BC337 BC338	I_{CES}	— —	— —	100 100	nAdc
Emitter Cutoff Current ($V_{EB} = 4.0$ V, $I_C = 0$)		I_{EBO}	—	—	100	nAdc
ON CHARACTERISTICS						
DC Current Gain ($I_C = 100$ mA, $V_{CE} = 1.0$ V) ($I_C = 300$ mA, $V_{CE} = 1.0$ V)	BC337/BC338 BC337-16/BC338-16 BC337-25/BC338-25 BC337-40/BC338-40	h_{FE}	100 100 160 250 60	— — — — —	630 250 400 630 —	—
Base-Emitter On Voltage ($I_C = 300$ mA, $V_{CE} = 1.0$ V)		$V_{BE(on)}$	—	—	1.2	Vdc
Collector-Emitter Saturation Voltage ($I_C = 500$ mA, $I_B = 50$ mA)		$V_{CE(sat)}$	—	—	0.7	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Output Capacitance ($V_{CB} = 10$ V, $I_E = 0$, f = 1.0 MHz)		C_{ob}	—	15	—	pF
Current-Gain Bandwidth Product ($I_C = 10$ mA, $V_{CE} = 5.0$ V)		f_T	—	210	—	MHz

FIGURE 1 — THERMAL RESPONSE

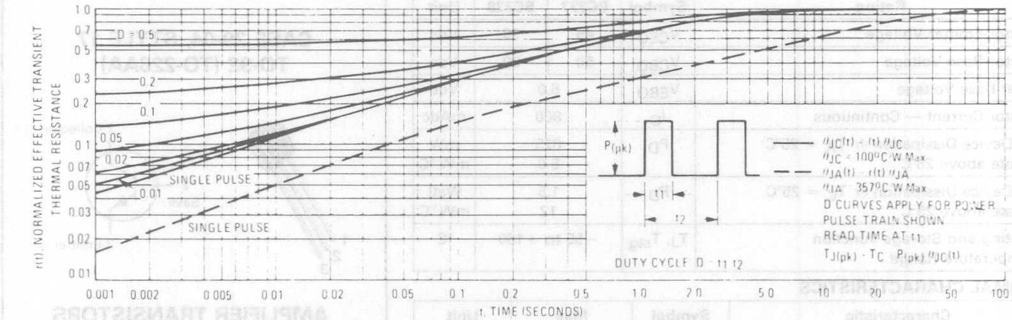


FIGURE 2 — ACTIVE REGION SAFE OPERATING AREA

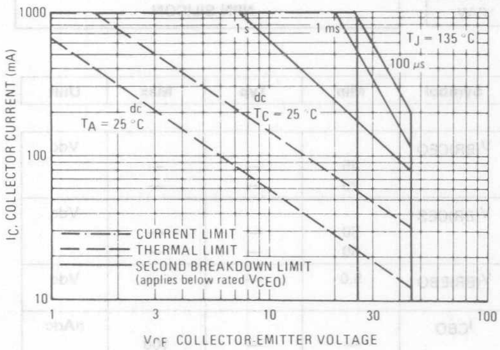


FIGURE 3 — DC CURRENT GAIN

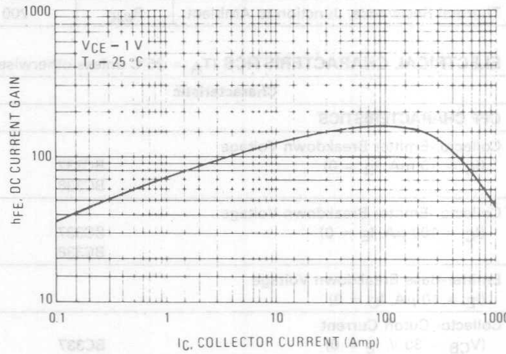


FIGURE 4 — SATURATION REGION

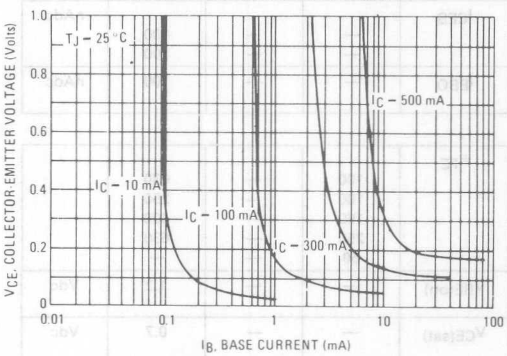


FIGURE 5 — "ON" VOLTAGES

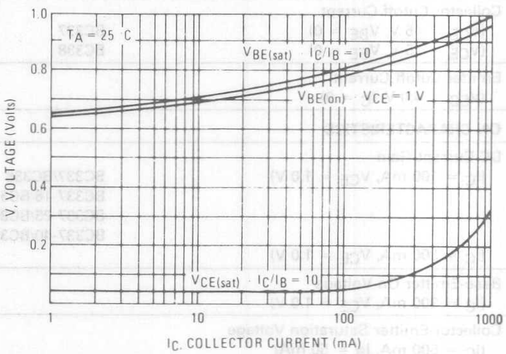


FIGURE 6 – TEMPERATURE COEFFICIENTS

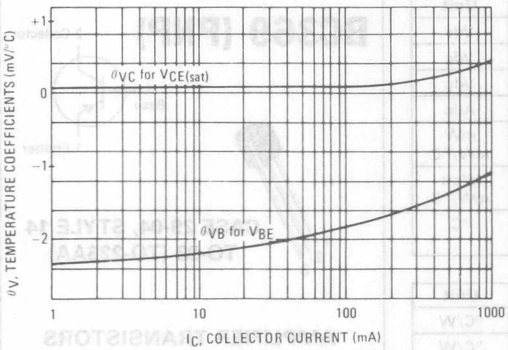
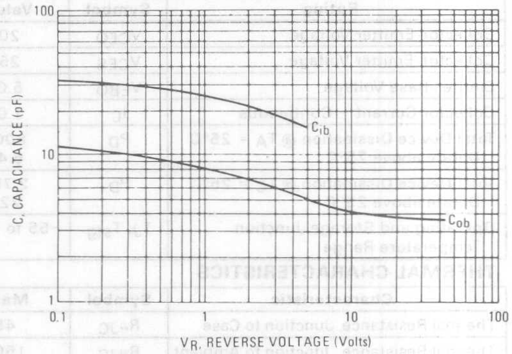
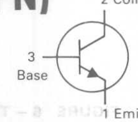


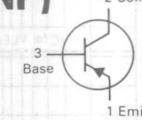
FIGURE 7 – CAPACITANCES



BC368 (NPN)



BC369 (PNP)



CASE 29-04, STYLE 14
TO-92 (TO-226AA)

AMPLIFIER TRANSISTORS

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	20	Vdc
Collector-Emitter Voltage	V_{CES}	25	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous	I_C	1.0	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	800 6.4	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.75 22	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	45	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	156	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 10$ mA, $I_B = 0$)	$V_{(BR)CEO}$	20	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$A, $I_E = 0$)	$V_{(BR)CBO}$	25	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu$A, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 25$ V, $I_E = 0$) ($V_{CB} = 25$ V, $I_E = 0$, $T_J = 150°C$)	I_{CBO}	 — —	 — —	 10 1.0	 μAdc mAdc
Emitter Cutoff Current ($V_{EB} = 5.0$ V, $I_C = 0$)	I_{EBO}	—	—	10	μAdc
ON CHARACTERISTICS					
DC Current Gain ($V_{CE} = 10$ V, $I_C = 5.0$ mA) ($V_{CE} = 1.0$ V, $I_C = 0.5$ A) ($V_{CE} = 1.0$ V, $I_C = 1.0$ A)	h_{FE}	 50 85 60	 — — —	 — 375 —	—
Bandwidth Product ($I_C = 10$ mA, $V_{CE} = 5.0$ V, f = 20 MHz)	f_T	65	—	—	MHz
Collector-Emitter Saturation Voltage ($I_C = 1.0$ A, $I_B = 100$ mA)	$V_{CE(sat)}$	—	—	0.5	V
Base-Emitter On Voltage ($I_C = 1.0$ A, $V_{CE} = 1.0$ V)	$V_{BE(on)}$	—	—	1.0	V

FIGURE 1 — DC CURRENT GAIN

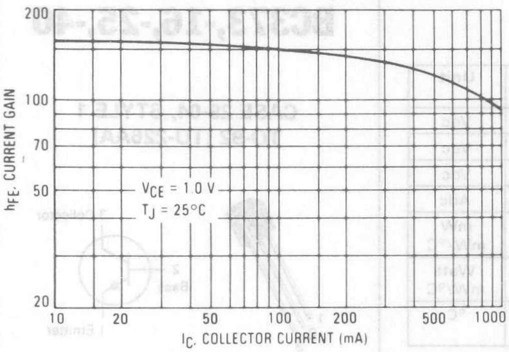


FIGURE 2 — COLLECTOR SATURATION REGION

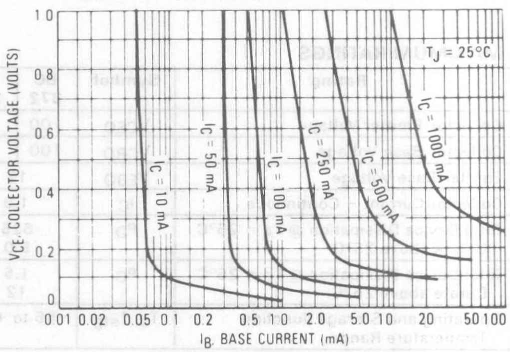


FIGURE 3 — ON VOLTAGES

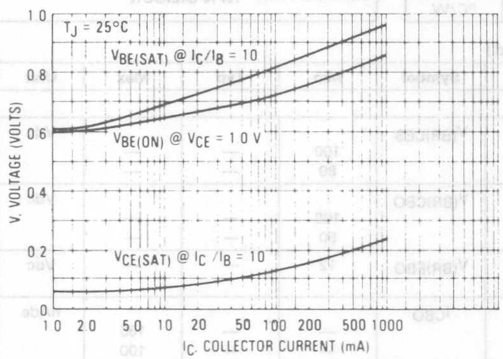


FIGURE 4 — TEMPERATURE COEFFICIENT

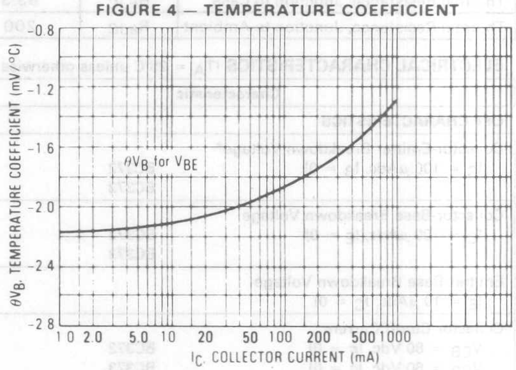


FIGURE 5 — CURRENT GAIN-BANDWIDTH PRODUCT

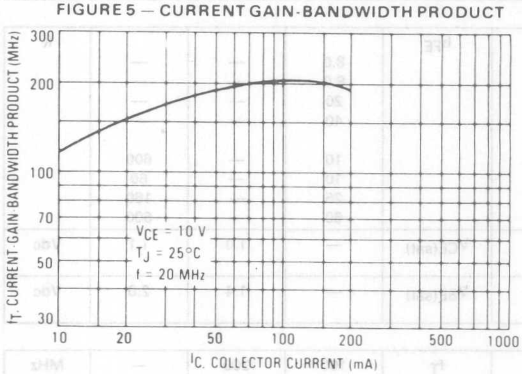
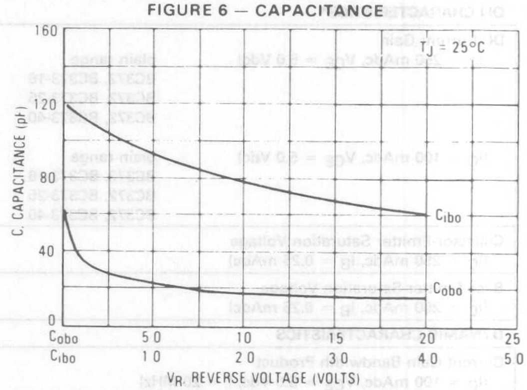


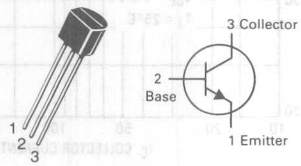
FIGURE 6 — CAPACITANCE



2

BC373,-16,-25,-40

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



HIGH VOLTAGE DARLINGTON

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	BC 372	BC 373	Unit
Collector-Emitter Voltage	V_{CEO}	100	80	Vdc
Collector-Base Voltage	V_{CBO}	100	80	Vdc
Emitter-Base Voltage	V_{EBO}	12		Vdc
Collector Current — Continuous	I_C	1.0		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

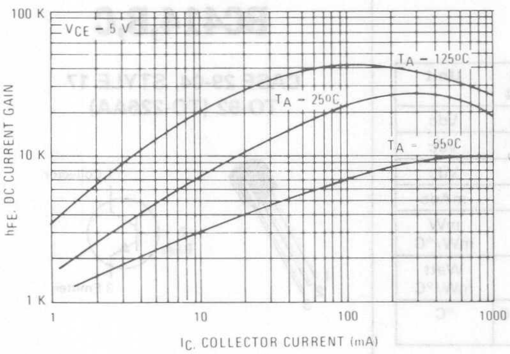
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage* (I_C = 100 μAdc, I_B = 0)	BC372 BC373	$V_{(BR)CES}$	100 80	— —	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	BC372 BC373	$V_{(BR)CBO}$	100 80	— —	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	12	—	—	Vdc
Collector Cutoff Current (V_{CB} = 80 Vdc, I_E = 0) (V_{CB} = 60 Vdc, I_E = 0)	BC372 BC373	I_{CBO}			100 100	nAdc
Emitter Cutoff Current (V_{BE} = 10 V, I_C = 0)		I_{EBO}	—	—	100	nAdc
ON CHARACTERISTICS*						
DC Current Gain (I_C = 250 mAdc, V_{CE} = 5.0 Vdc)	plain range BC372, BC373-16 BC372, BC373-25 BC372, BC373-40	h_{FE}	8.0 8.0 20 40	— — — —	— — — —	K
(I_C = 100 mAdc, V_{CE} = 5.0 Vdc)	plain range BC372, BC373-16 BC372, BC373-25 BC372, BC373-40		10 10 25 60	— — — —	600 60 160 600	
Collector-Emitter Saturation Voltage (I_C = 250 mAdc, I_B = 0.25 mAdc)		$V_{CE(sat)}$	—	1.0	1.1	Vdc
Base-Emitter Saturation Voltage (I_C = 250 mAdc, I_B = 0.25 mAdc)		$V_{BE(sat)}$	—	1.4	2.0	Vdc
DYNAMIC CHARACTERISTICS						
Current-Gain Bandwidth Product (I_C = 100 mAdc, V_{CE} = 5.0 Vdc, f = 20 MHz)		f_T	100	200	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{ob}	—	10	25	pF
Noise Figure (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, R_g = 100 kohm, F = 1.0 kHz)		NF	—	2.0	—	dB

*Pulse Test: Pulse Width = 300 μs, Duty Cycle 2.0%.



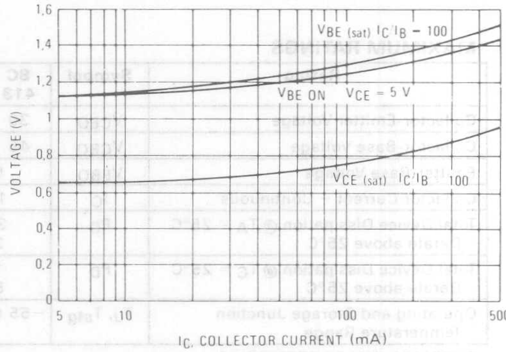


FIGURE 3 – CURRENT GAIN BANDWIDTH PRODUCT

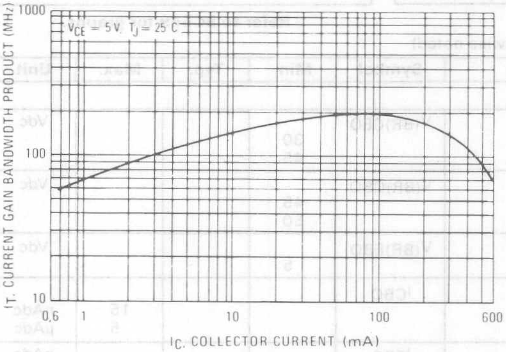
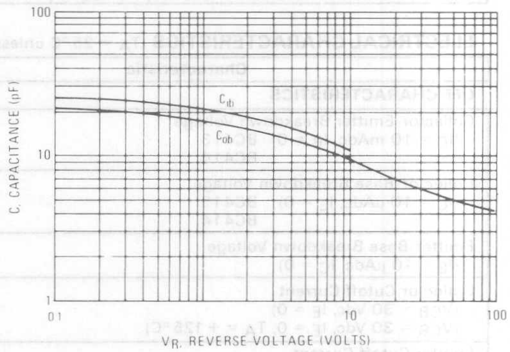
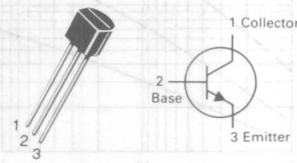


FIGURE 4 – CAPACITANCES



BC413,B,C
BC414,B,C

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



LOW NOISE TRANSISTORS

NPN SILICON

Refer to BC549 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BC 413	BC 414	Unit
Collector-Emitter Voltage	V_{CEO}	30	45	Vdc
Collector-Base Voltage	V_{CBO}	45	50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current – Continuous	I_C	100		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	350 2.8		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.0 8.0		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	357	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted)

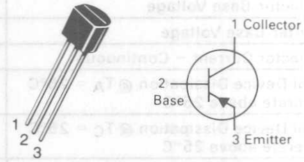
Characteristic	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0) BC413 BC414	$V_{(BR)CEO}$	 30 45			Vdc
Collector-Base Breakdown Voltage (I_C = 10 µAdc, I_E = 0) BC413 BC414	$V_{(BR)CBO}$	 45 50			Vdc
Emitter-Base Breakdown Voltage (I_E = 10 µAdc, I_C = 0)	$V_{(BR)EBO}$	 5			Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0) (V_{CB} = 30 Vdc, I_E = 0, T_A = +125°C)	I_{CBO}			 15 5	 nAdc µAdc
Emitter Cutoff Current (V_{EB} = 4 Vdc, I_C = 0)	I_{EBO}			 15	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 10 µAdc, V_{CE} = 5 Vdc) BC413B/BC414B BC413C/BC414C (I_C = 2 mAdc, V_{CE} = 5 Vdc) BC413B/BC414B BC413C/BC414C BC413/BC414	h_{FE}	 100 100 180 380 180	 150 270 290 500 350	 460 800 800	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.5 mAdc) (I_C = 10 mAdc, I_B = see note 1) (I_C = 100 mAdc, I_B = 5 mAdc, see note 2)	$V_{CE(sat)}$		 0.075 0.3 0.25	 0.25 0.6 0.6	Vdc
Base-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 5 mAdc)	$V_{BE(sat)}$		 1.1		Vdc
Base-Emitter On Voltage (I_C = 10 µAdc, V_{CE} = 5 Vdc) (I_C = 100 µAdc, V_{CE} = 5 Vdc) (I_C = 2 mAdc, V_{CE} = 5 Vdc)	$V_{BE(on)}$	 0.55	 0.52 0.55 0.62	 0.75	Vdc
SMALL SIGNAL CHARACTERISTICS					
Current-Gain-Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5 Vdc, f = 100 MHz)	f_T		 250		MHz
Collector-Base Capacitance (V_{CE} = 10 Vdc, I_E = 0, f = 1 MHz)	C_{cbo}		 2.5		pF
Noise Figure (I_C = 200 µAdc, V_{CE} = 5 Vdc, R_S = 2 KΩ, f = 30 Hz – 15 KHz)	NF		 0.6	 2.5	dB

Note 1: I_B is value for which I_C = 11 mA at V_{CE} = 1 V

Note 2: Pulse test = 300 µs – Duty cycle = 2%

BC415,B,C
BC416,B,C

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



LOW NOISE TRANSISTORS

PNP SILICON

2

MAXIMUM RATINGS

Rating	Symbol	BC 415	BC 416	Unit
Collector-Emitter Voltage	V_{CEO}	35	45	Vdc
Collector-Base Voltage	V_{CBO}	45	50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current − Continuous	I_C	100		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25 °C unless otherwise noted)

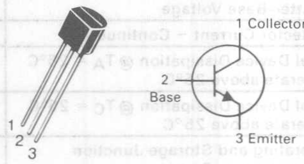
Characteristic	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0) BC415 BC416	$V_{(BR)CEO}$	 35 45			Vdc
Collector-Base Breakdown Voltage (I_C = 10 µAdc, I_E = 0) BC415 BC416	$V_{(BR)CBO}$	 45 50			Vdc
Emitter-Base Breakdown Voltage (I_E = 10 µAdc, I_C = 0)	$V_{(BR)EBO}$	5			Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0) (V_{CB} = 30 Vdc, I_E = 0, T_A = + 125 °C)	I_{CBO}			 15 5	 nAdc µAdc
Emitter Cutoff Current (V_{EB} = 4 Vdc, I_C = 0)	I_{EBO}			15	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 10 µAdc, V_{CE} = 5 Vdc) BC415B/BC416B BC415C/BC416C (I_C = 2 mAdc, V_{CE} = 5 Vdc) BC415B/BC416B BC415C/BC416C BC415/BC416	h_{FE}	 100 100 180 380 120	 150 270 290 500 350	 460 800 800	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.5 mAdc) (I_C = 10 mAdc, I_B = see note 1) (I_C = 100 mAdc, I_B = 5 mAdc, see note 2)	$V_{CE(sat)}$		 0.075 0.3 0.25	 0.25 0.6	Vdc
Base-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 5 mAdc)	$V_{BE(sat)}$		1.1		Vdc
Base-Emitter On Voltage (I_C = 10 µAdc, V_{CE} = 5 Vdc) (I_C = 100 µAdc, V_{CE} = 5 Vdc) (I_C = 2 mAdc, V_{CE} = 5 Vdc)	$V_{BE(on)}$	 0.55	 0.52 0.55 0.62	 0.75	Vdc
SMALL SIGNAL CHARACTERISTICS					
Current-Gain-Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5 Vdc, f = 100 MHz)	f_T		250		MHz
Collector-Base Capacitance (V_{CE} = 10 Vdc, I_E = 0, f = 1 MHz)	C_{cbo}		2.5		pF
Noise Figure (I_C = 200 µAdc, V_{CE} = 5 Vdc, R_S = 2 KΩ, f = 30 Hz − 15 KHz)	NF		0.5	2.0	dB

Note 1: I_B is value for which I_C = 11 mA at V_{CE} = 1 V

Note 2: Pulse test = 300 µs − Duty cycle = 2%

BC447,A,B
BC449,A,B

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



HIGH VOLTAGE TRANSISTORS

NPN SILICON

2

MAXIMUM RATINGS

Rating	Symbol	BC 445	BC 447	BC 449	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	100	Vdc
Collector-Base Voltage	V_{CBO}	60	80	100	Vdc
Emitter-Base Voltage	V_{EBO}	5.0			Vdc
Collector Current — Continuous	I_C	300			mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0			mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12			Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

Refer to MPS8098 for graphs.

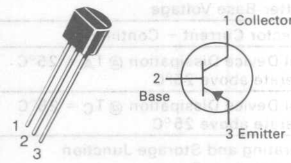
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage* (I_C = 1.0 mAdc, I_B = 0)	BC445 BC447 BC449	$V_{(BR)CEO}$	60 80 100	— — —	— — —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μA, I_E = 0)	BC445 BC447 BC449	$V_{(BR)CBO}$	60 80 100	— — —	— — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 40 Vdc, I_E = 0) (V_{CB} = 60 Vdc, I_E = 0) (V_{CB} = 80 Vdc, I_E = 0)	BC445 BC447 BC449	I_{CBO}	— — —	— — —	100 100 100	nAdc
ON CHARACTERISTICS*						
DC Current Gain (I_C = 2.0 mA, V_{CE} = 5.0 V)	BC445/447/449 BC445A/447A/449A BC447B/449B	h_{FE}	50 120 180	— — —	460 220 460	—
(I_C = 10 mA, V_{CE} = 5.0 V)	BC445/447/449 BC445A/447A/449A BC447B/449B		50 100 160			
(I_C = 100 mA, V_{CE} = 5.0 V)	BC445/447/449 BC445A/447A/449A BC447B/449B		50 60 90			
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 10 mAdc)		$V_{CE(sat)}$	—	0.1	0.25	Vdc
Base-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 10 mAdc)		$V_{BE(sat)}$	—	0.85	—	Vdc
Base-Emitter On Voltage (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 100 mA, V_{CE} = 5.0 V)*		$V_{BE(on)}$	0.55 —	 0.8	0.7 1.2	Vdc
DYNAMIC CHARACTERISTICS						
Current-Gain Bandwidth Product (I_C = 50 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)		f_T	100	250		MHz

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle 2.0%.

BC446,A,B
BC448,A,B
BC450,A,B

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



HIGH VOLTAGE TRANSISTORS

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	BC 446	BC 448	BC 450	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	100	Vdc
Collector-Base Voltage	V_{CBO}	60	80	100	Vdc
Emitter-Base Voltage	V_{EBO}		5.0		Vdc
Collector Current — Continuous	I_C		300		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D		625 5.0		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D		1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

Refer to MPS8598 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

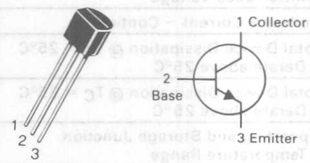
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage* ($I_C = 1.0$ mAdc, $I_B = 0$)	 BC446 BC448 BC450	$V_{(BR)CEO}$	 60 80 100	 — — —	 — — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μA, $I_E = 0$)	 BC446 BC448 BC450	$V_{(BR)CBO}$	 60 80 100	 — — —	 — — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 40$ Vdc, $I_E = 0$) ($V_{CB} = 60$ Vdc, $I_E = 0$) ($V_{CB} = 80$ Vdc, $I_E = 0$)	 BC446 BC448 BC450	I_{CBO}	 — — —	 — — —	 100 100 100	nAdc
ON CHARACTERISTICS*						
DC Current Gain ($I_C = 2.0$ mA, $V_{CE} = 5.0$ V) ($I_C = 10$ mA, $V_{CE} = 5.0$ V) ($I_C = 100$ mA, $V_{CE} = 5.0$ V)	 BC446/448/450 BC446A/448A/450A BC446B/448B/450B BC446/448/450 BC446A/448A/450A BC446B/448B/450B BC446/448/450 BC446A/448A/450A BC446B/448B/450B	h_{FE}	 50 120 180 50 100 160 50 60 90	 — — — — — — — — —	 460 220 460 — — — — — —	
Collector-Emitter Saturation Voltage ($I_C = 100$ mAdc, $I_B = 10$ mAdc)		$V_{CE(sat)}$	—	0.125	0.25	Vdc
Base-Emitter Saturation Voltage ($I_C = 100$ mAdc, $I_B = 10$ mAdc)		$V_{BE(sat)}$	—	0.85		Vdc
Base-Emitter On Voltage ($I_C = 2.0$ mA, $V_{CE} = 5.0$ V) ($I_C = 100$ mA, $V_{CE} = 5.0$ V)*		$V_{BE(on)}$	 0.55 —	 — 0.76	 0.7 1.2	Vdc
DYNAMIC CHARACTERISTICS						
Current-Gain-Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 5.0$ Vdc, f = 100 MHz)		f_T	100	200	—	MHz

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle 2.0%.

2

BC485,A,B,L
BC487,A,B,L
BC489,A,B,L

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



HIGH CURRENT TRANSISTORS

NPN SILICON

Refer to MPSA05 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BC 485	BC 487	BC 489	Unit
Collector-Emitter Voltage	V_{CEO}	45	60	80	Vdc
Collector-Base Voltage	V_{CBO}	45	60	80	Vdc
Emitter-Base Voltage	V_{EBO}		5.0		Vdc
Collector Current − Continuous	I_C		1.0		Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D		625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D		1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

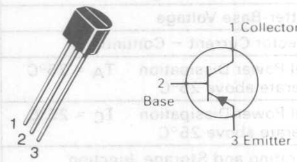
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage*	$V_{(BR)CEO}$				Vdc
(I_C = 10 mAdc, I_B = 0) BC485		45	—	—	
BC487		60	—	—	
BC489		80	—	—	
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$				Vdc
(I_C = 100 μAdc, I_E = 0) BC485		45	—	—	
BC487		60	—	—	
BC489		80	—	—	
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0			Vdc
Collector Cutoff Current	I_{CBO}				nAdc
V_{CB} = 30 Vdc − I_E = 0 BC485		—	—	100	
V_{CB} = 40 Vdc − I_E = 0 BC487		—	—	100	
V_{CB} = 60 Vdc − I_E = 0 BC489		—	—	100	
ON CHARACTERISTICS*					
DC Current Gain	h_{FE}				
(I_C = 10 mAdc − V_{CE} = 2.0 Vdc)		40			
(I_C = 100 mAdc − V_{CE} = 2.0 Vdc) BC485/487/489		60		400	
BC485L/487L/489L		60	120	150	
BC485A/487A/489A		100	160	250	
BC485B/487B/489B		160	260	400	
(I_C = 1 Adc − V_{CE} = 5.0 Vdc)*		15			
Collector Emitter Saturation Voltage	$V_{CE(sat)}$				Vdc
(I_C = 500 mAdc − I_B = 50 mAdc)		—	0.2	0.50	
(I_C = 1 Adc − I_B = 100 mAdc)		—	0.3	—	
Base Emitter Saturation Voltage	$V_{BE(sat)}$				Vdc
(I_C = 500 mAdc, I_B = 50 mAdc)		—	0.85	1.20	
(I_C = 1 Adc − I_B = 100 mAdc)*			0.90		
DYNAMIC CHARACTERISTICS					
Current-Gain-Bandwidth Product (I_C = 50 mAdc, V_{CE} = 2.0 Vdc, f = 100 MHz)	f_T	—	200	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{ob}	—	7	—	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ib}	—	50		pF

*Pulse test - Pulse width = 300 μs - Duty Cycle 2%.

BC486,A,B,L
BC488,A,B,L
BC490,A,B,L

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



HIGH CURRENT TRANSISTORS

PNP SILICON

Refer to MPSA55 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BC 486	BC 488	BC 490	Unit
Collector-Emitter Voltage	V_{CEO}	45	60	80	Vdc
Collector-Base Voltage	V_{CBO}	45	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	4.0			Vdc
Collector Current — Continuous	I_C	1.0			Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0			mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12			Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage* ($I_C = 10$ mAdc, $I_B = 0$) BC486 BC488 BC490	$V_{(BR)CEO}$	 45 60 80	 — — —		Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ µAdc, $I_E = 0$) BC486 BC488 BC490	$V_{(BR)CBO}$	 45 60 80	 — — —		Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ µAdc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—		Vdc
Collector Cutoff Current $V_{CB} = 30$ Vdc − $I_E = 0$ BC486 $V_{CB} = 40$ Vdc − $I_E = 0$ BC488 $V_{CB} = 60$ Vdc − $I_E = 0$ BC490	I_{CBO}	 — — —	 — — —	 100 100 100	nAdc
ON CHARACTERISTICS*					
DC Current Gain ($I_C = 10$ mAdc − $V_{CE} = 2.0$ Vdc) ($I_C = 100$ mAdc − $V_{CE} = 2.0$ Vdc) BC486/488/490 BC486L/488L/490L BC486A/488A/490A BC486B/488B/490B ($I_C = 1$ Adc — $V_{CE} = 5.0$ Vdc)	h_{FE}	 40 60 60 100 160 15	 — 100 140 260 	 400 150 250 400 	
Collector Emitter Saturation Voltage ($I_C = 500$ mAdc − $I_B = 50$ mAdc) ($I_C = 1$ Adc − $I_B = 100$ mAdc)	$V_{CE(sat)}$	 — —	 0.25 0.50	 0.50 	Vdc
Base Emitter Saturation Voltage ($I_C = 500$ mAdc, $I_B = 50$ mAdc) ($I_C = 1$ Adc − $I_B = 100$ mAdc)	$V_{BE(sat)}$		 0.90 1.00	 1.20 	Vdc
DYNAMIC CHARACTERISTICS					
Current-Gain-Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 2.0$ Vdc, f = 100 MHz)	f_T	—	150	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{ob}	—	9	—	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)	C_{ib}	—	110	—	pF

* Pulse test - Pulse width = 300 µs - Duty Cycle 2%.

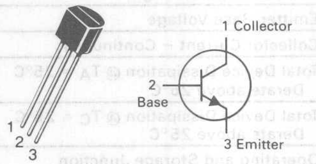
MAXIMUM RATINGS

Rating	Symbol	BC517	Unit
Collector-Emitter Voltage	V_{CES}	30	Vdc
Collector-Base Voltage	V_{CB}	40	Vdc
Emitter-Base Voltage	V_{EB}	10	Vdc
Collector Current – Continuous	I_C	1.0	Adc
Total Power Dissipation $T_A = 25°C$ Derate above 25°C	P_D	625 12	mW mW/°C
Total Power Dissipation $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

CASSE 29-04, STYLE 17
TO-92 (TO-226AA)



DARLINGTON TRANSISTOR

NPN SILICON

Refer to 2N6426 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 2.0 mAdc, V_{BE} = 0)		$V_{(BR)CES}$	30	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 nAdc, I_C = 0)		$V_{(BR)EBO}$	10	—	—	Vdc
Collector Cutoff Current		I_{CES}				nA
(V_{CE} = 30 V)	BC517		—	—	500	
(V_{CE} = 20 V)	BC517S		—	—	5.0	
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)		I_{CBO}	—	—	100	nAdc
Emitter Cutoff Current (V_{BE} = 10 Vdc, I_C = 0)		I_{EBO}	—	—	100	nAdc
ON CHARACTERISTICS (1)						
DC Current Gain		h_{FE}				—
(I_C = 20 mAdc, V_{CE} = 2.0 V)			30,000	—	—	
(I_C = 180 mAdc, V_{CE} = 1.2 V)	BC517S		33,000	—	—	
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 0.1 mAdc)		$V_{CE(sat)}$	—	—	1.0	Vdc
Base-Emitter On Voltage (I_C = 10 mAdc, V_{CE} = 5.0 Vdc)		$V_{BE(on)}$	—	—	1.4	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain-Bandwidth Product (2) (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)		f_T	—	200	—	MHz

(1) Pulse Test Pulse Width ≤ 2.0%.
(2) $f_T = |h_{fe}| \bullet f_{test}$

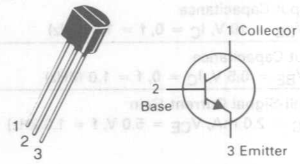
MAXIMUM RATINGS

Rating	Symbol	BC 546	BC 547	BC 548	Unit
Collector-Emitter Voltage	V_{CEO}	65	45	30	Vdc
Collector-Base Voltage	V_{CBO}	80	50	30	Vdc
Emitter-Base Voltage	V_{EBO}	6.0			Vdc
Collector Current – Continuous	I_C	100			mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0			mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12			Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

NPN SILICON

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mA, $I_B = 0$)	BC546 BC547 BC548	$V_{(BR)CEO}$	65 45 30	— — —	— — —	V
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc)	BC546 BC547 BC548	$V_{(BR)CBO}$	80 50 30	— — —	— — —	V
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$A, $I_C = 0$)	BC546 BC547 BC548	$V_{(BR)EBO}$	6.0 6.0 6.0	— — —	— — —	V
Collector Cutoff Current ($V_{CE} = 70$ V, $V_{BE} = 0$) ($V_{CE} = 50$ V, $V_{BE} = 0$) ($V_{CE} = 35$ V, $V_{BE} = 0$) ($V_{CE} = 30$ V, $T_A = 125°C$)	 BC546 BC547 BC548 BC546/547/548	I_{CES}	 — — — —	 0.2 0.2 0.2 —	 15 15 15 4.0	 nA μA
ON CHARACTERISTICS						
DC Current Gain ($I_C = 10\ \mu$A, $V_{CE} = 5.0$ V)	 BC546A/547A/548A BC546B/547B/548B BC548C	h_{FE}	 — — —	 90 150 270	 — — —	—
($I_C = 2.0$ mA, $V_{CE} = 5.0$ V)	BC546 BC547 BC548 BC546A/547A/548A BC546B/547B/548B BC547C/BC548C		110 110 110 110 200 420	— — — 180 290 520	450 800 800 220 450 800	
($I_C = 100$ mA, $V_{CE} = 5.0$ V)	BC546A/547A/548A BC546B/547B/548B BC548C		— — —	120 180 300	— — —	
Collector-Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 0.5$ mA) ($I_C = 100$ mA, $I_B = 5.0$ mA) ($I_C = 10$ mA, I_B = See Note 1)		$V_{CE(sat)}$	 — — —	 0.09 0.2 0.3	 0.25 0.6 0.6	V
Base-Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 0.5$ mA)		$V_{BE(sat)}$	—	0.7	—	V
Base-Emitter On Voltage ($I_C = 2.0$ mA, $V_{CE} = 5.0$ V) ($I_C = 10$ mA, $V_{CE} = 5.0$ V)		$V_{BE(on)}$	 0.55 —	 — —	 0.7 0.77	V

NOTE 1: I_B is value for which $I_C = 11$ mA at $V_{CE} = 1.0$ V.

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain Bandwidth Product (I_C = 10 mA, V_{CE} = 5.0 V, f = 100 MHz)		f_T				MHz
	BC546		150	300	—	
	BC547		150	300	—	
	BC548		150	300	—	
Output Capacitance (V_{CB} = 10 V, I_C = 0, f = 1.0 MHz)		C_{obo}	—	1.7	4.5	pF
Input Capacitance (V_{BE} = 0.5 V, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	10	—	pF
Small-Signal Current Gain (I_C = 2.0 mA, V_{CE} = 5.0 V, f = 1.0 kHz)		h_{fe}				
	BC546		125	—	500	
	BC547/548		125	—	900	
	BC546A/547A/548A		125	220	260	
	BC546B/547B/548B		240	330	500	
	BC547C/548C		450	600	900	
Noise Figure (I_C = 0.2 mA, V_{CE} = 5.0 V, R_S = 2 kohms, f = 1.0 kHz, Δf = 200 Hz)		NF				dB
	BC546		—	2.0	10	
	BC547		—	2.0	10	
	BC548		—	2.0	10	

BC547/BC548

FIGURE 1 – NORMALIZED DC CURRENT GAIN

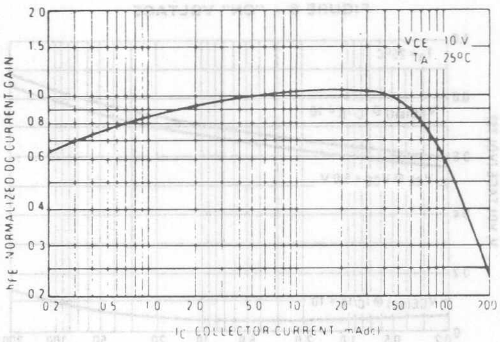


FIGURE 2 – "SATURATION" AND "ON" VOLTAGES

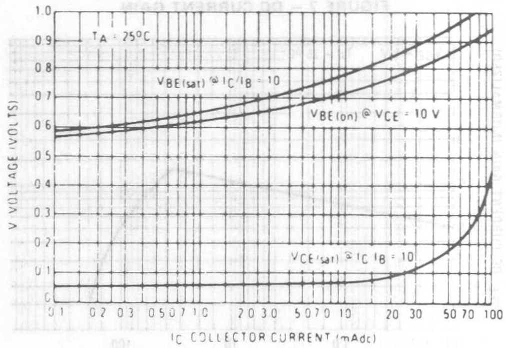


FIGURE 3 – COLLECTOR SATURATION REGION

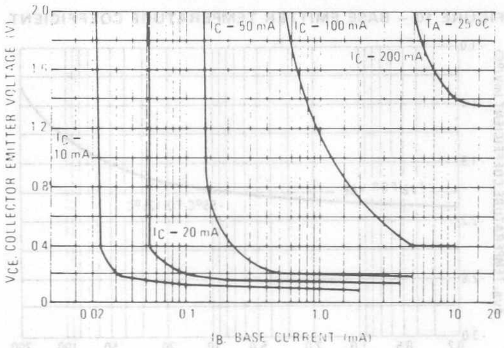


FIGURE 4 – BASE EMITTER TEMPERATURE COEFFICIENT

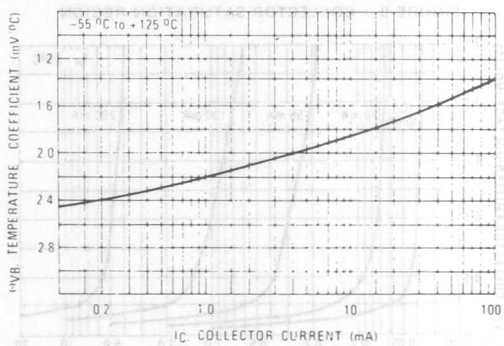


FIGURE 5 – CAPACITANCES

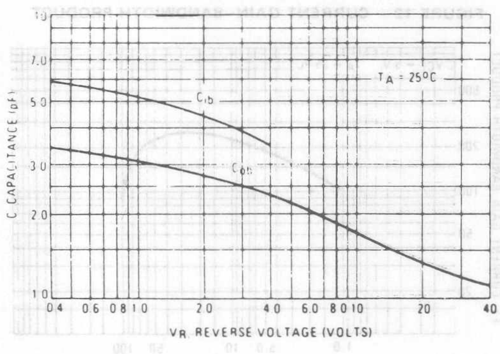


FIGURE 6 – CURRENT GAIN–BANDWIDTH PRODUCT

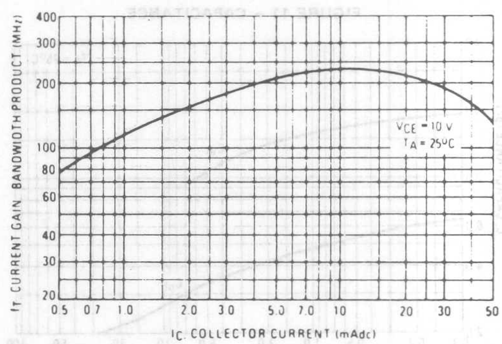


FIGURE 7 – DC CURRENT GAIN

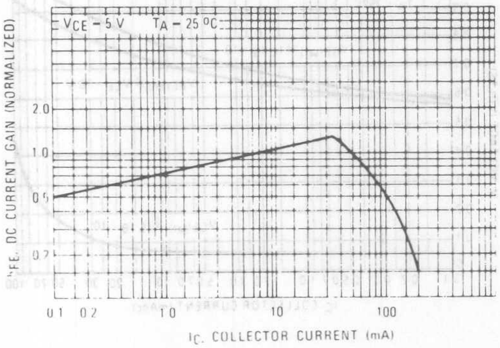


FIGURE 8 – "ON" VOLTAGE

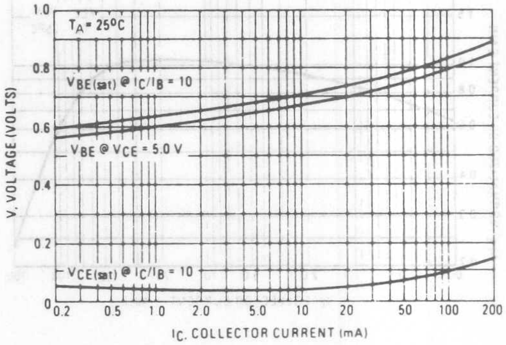


FIGURE 9 – COLLECTOR SATURATION REGION

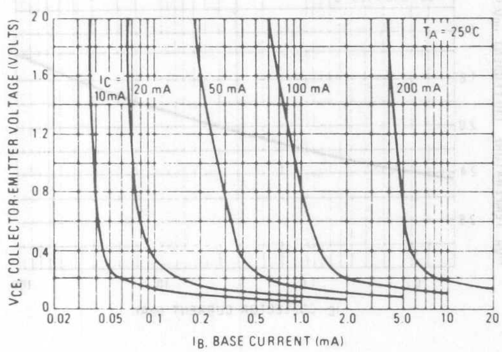


FIGURE 10 – BASE EMITTER TEMPERATURE COEFFICIENT

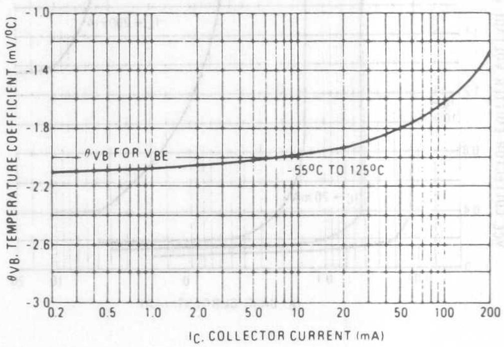


FIGURE 11 – CAPACITANCE

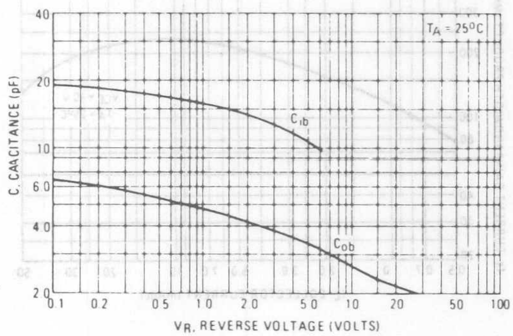
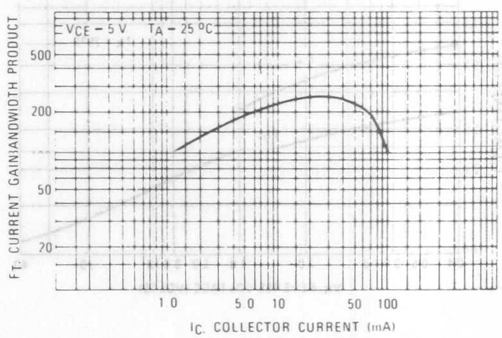
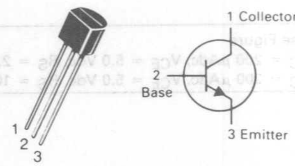


FIGURE 12 – CURRENT GAIN–BANDWIDTH PRODUCT



BC549,A,B,C
BC550,B,C

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



LOW NOISE TRANSISTORS

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	BC 549	BC 550	Unit
Collector-Emitter Voltage	V_{CEO}	30	45	Vdc
Collector-Base Voltage	V_{CBO}	30	50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current – Continuous	I_C	100		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0) BC549 BC550	$V_{(BR)CEO}$	 30 45			Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0) BC549 BC550	$V_{(BR)CBO}$	 30 50			Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5			Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0) (V_{CB} = 30 Vdc, I_E = 0, T_A = +125°C)	I_{CBO}			 15 5	 nAdc μAdc
Emitter Cutoff Current (V_{EB} = 4 Vdc, I_C = 0)	I_{EBO}			 15	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 10 μAdc, V_{CE} = 5 Vdc) BC549B/550B BC549C/550C (I_C = 2 mAdc, V_{CE} = 5 Vdc) BC549A BC549B/550B BC549C/550C BC549/550	h_{FE}	 100 100 110 200 420 110	 150 270 290 500 	 220 450 800 800	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.5 mAdc) (I_C = 10 mAdc, I_B = see note 1) (I_C = 100 mAdc, I_B = 5 mAdc, see note 2)	$V_{CE(sat)}$		 0.075 0.3 0.25	 0.25 0.6 0.6	Vdc
Base-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 5 mAdc)	$V_{BE(sat)}$		 1.1		Vdc
Base-Emitter On Voltage (I_C = 10 μAdc, V_{CE} = 5 Vdc) (I_C = 100 μAdc, V_{CE} = 5 Vdc) (I_C = 2 mAdc, V_{CE} = 5 Vdc)	$V_{BE(on)}$	 0.55	 0.52 0.55 0.62	 0.7	Vdc
SMALL SIGNAL CHARACTERISTICS					
Current-Gain-Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5 Vdc, f = 100 MHz)	f_T		 250		MHz
Collector-Base Capacitance (V_{CE} = 10 Vdc, I_E = 0, f = 1 MHz)	C_{cbo}		 2.5		pF

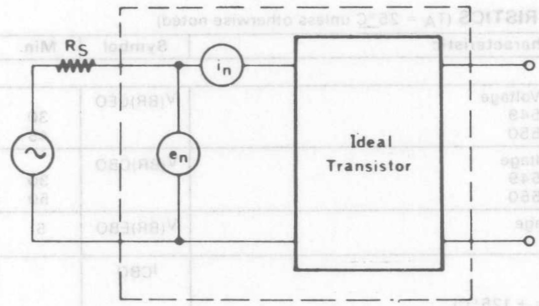
Note 1: I_B is value for which I_C = 11 mA at V_{CE} = 1 V

Note 2: Pulse test = 300 μs – Duty cycle = 2%

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Small-Signal Current Gain (I_C = 2.0 mAdc, V_{CE} = 5.0 V, f = 1.0 kHz)	h_{fe}				—
BC549/BC550		125	—	900	
BC549B/BC550B		240	330	500	
BC549C/BC550C		450	600	900	
Noise Figure					dB
(I_C = 200 μAdc, V_{CE} = 5.0 Vdc, R_S = 2.0 kΩ, f = 30 Hz–15 kHz)	NF_1	—	0.6	2.5	
(I_C = 200 μAdc, V_{CE} = 5.0 Vdc, R_S = 100 kΩ, f = 1.0 kHz)	NF_2	—	—	10	

FIGURE 1 – TRANSISTOR NOISE MODEL



2

FIGURE 2 — NORMALIZED DC CURRENT GAIN

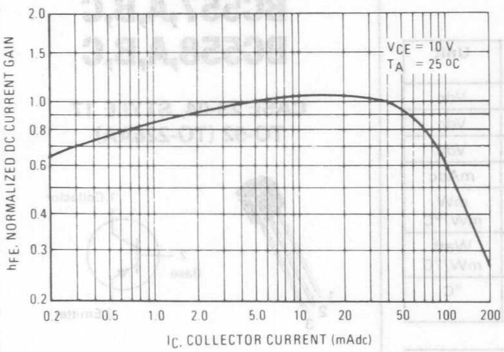


FIGURE 3 — "SATURATION" AND "ON" VOLTAGES

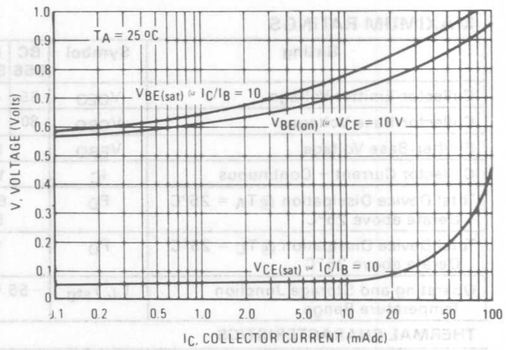


FIGURE 4 — CURRENT-GAIN BANDWIDTH PRODUCT

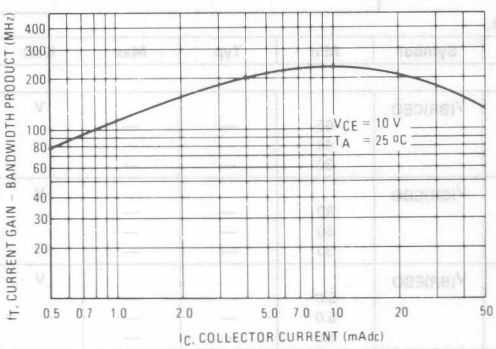


FIGURE 5 — CAPACITANCE

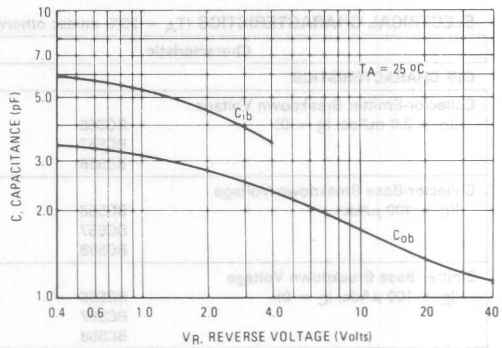
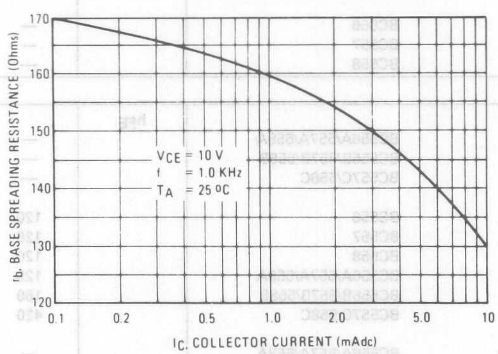


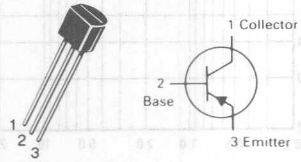
FIGURE 6 — BASE SPREADING RESISTANCE



2

BC556,A,B
BC557,A,B,C
BC558,A,B,C

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	BC 556	BC 557	BC 558	Unit
Collector-Emitter Voltage	V_{CEO}	65	45	30	Vdc
Collector-Base Voltage	V_{CBO}	80	50	30	Vdc
Emitter-Base Voltage	V_{EBO}	5.0			Vdc
Collector Current – Continuous	I_C	100			mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0			mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12			Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$				V
(I_C = 2.0 mAdc, I_B = 0)	BC556		65	—	—	
	BC557		45	—	—	
	BC558		30	—	—	
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$				V
(I_C = 100 μAdc)	BC556		80	—	—	
	BC557		50	—	—	
	BC558		30	—	—	
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$				V
(I_E = 100 μAdc, I_C = 0)	BC556		5.0	—	—	
	BC557		5.0	—	—	
	BC558		5.0	—	—	
Collector-Emitter Leakage Current		I_{CES}				nA
(V_{CES} = 40 V)	BC556		—	2.0	100	
(V_{CES} = 20 V)	BC557		—	2.0	100	
	BC558		—	2.0	100	
(V_{CES} = 20 V, T_A = 125°C)	BC556		—	—	4.0	
	BC557		—	—	4.0	μA
	BC558		—	—	4.0	
ON CHARACTERISTICS						
DC Current Gain		h_{FE}				—
(I_C = 10 μAdc, V_{CE} = 5.0 V)	BC556A/557A/558A		—	90	—	
	BC556B/557B/558B		—	150	—	
	BC557C/558C		—	270	—	
(I_C = 2.0 mAdc, V_{CE} = 5.0 V)	BC556		120	—	500	
	BC557		120	—	800	
	BC558		120	—	800	
	BC556A/557A/558A		120	170	220	
	BC556B/557B/558B		180	290	460	
	BC557C/558C		420	500	800	
(I_C = 100 mAdc, V_{CE} = 5.0 V)	BC556A/557A/558A		—	120	—	
	BC556B/557B/558B		—	180	—	
	BC557C/558C		—	300	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$				V
(I_C = 10 mAdc, I_B = 0.5 mAdc)			—	0.075	0.3	
(I_C = 10 mAdc, I_B = see Note 1)			—	0.3	0.6	
(I_C = 100 mAdc, I_B = 5.0 mAdc)			—	0.25	0.65	

NOTE 1: I_C = 10 mAdc on the constant base current characteristics, which yields the point I_C = 11 mAdc, V_{CE} = 1.0 V.

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS (continued)						
Base-Emitter Saturation Voltage		$V_{BE(sat)}$				V
(I_C = 10 mAdc, I_B = 0.5 mAdc)			—	0.7	—	
(I_C = 100 mAdc, I_B = 5.0 mAdc)			—	1.0	—	
Base-Emitter On Voltage		$V_{BE(on)}$				V
(I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)			0.55	0.62	0.7	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)			—	0.7	0.82	
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain Bandwidth Product		f_T				MHz
(I_C = 10 mA, V_{CE} = 5.0 V, f = 50 MHz)	BC556		—	280	—	
	BC557		—	320	—	
	BC558		—	360	—	
Output Capacitance (V_{CB} = 10 V, I_C = 0, f = 1.0 MHz)		C_{ob}	—	3.0	6.0	pF
Noise Figure		NF				dB
(I_C = 0.2 mAdc, V_{CE} = 5.0 V, R_S = 2 kohms,	BC556		—	2.0	10	
f = 1.0 kHz, Δf = 200 Hz)	BC557		—	2.0	10	
	BC558		—	2.0	10	
Small-Signal Current Gain		h_{fe}				—
(I_C = 2.0 mAdc, V_{CE} = 5.0 V, f = 1.0 kHz)	BC556		125	—	500	
	BC557/558		125	—	900	
	BC556A/557A/558A		125	220	260	
	BC556B/557B/558B		240	330	500	
	BC557C/558C		450	600	900	

BC557/BC558

FIGURE 1 – NORMALIZED DC CURRENT GAIN

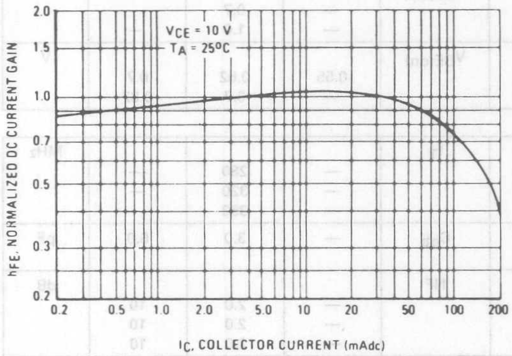


FIGURE 2 – "SATURATION" AND "ON" VOLTAGES

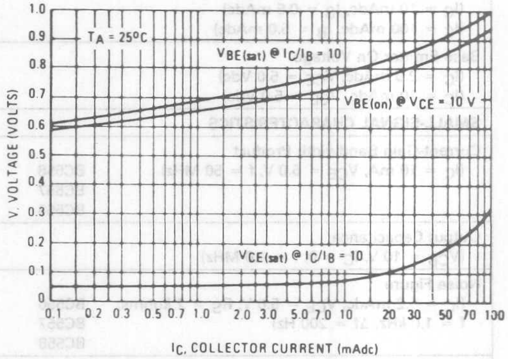


FIGURE 3 – COLLECTOR SATURATION REGION

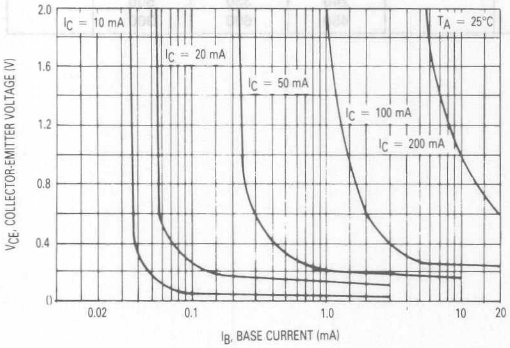


FIGURE 4 – BASE EMITTER TEMPERATURE COEFFICIENT

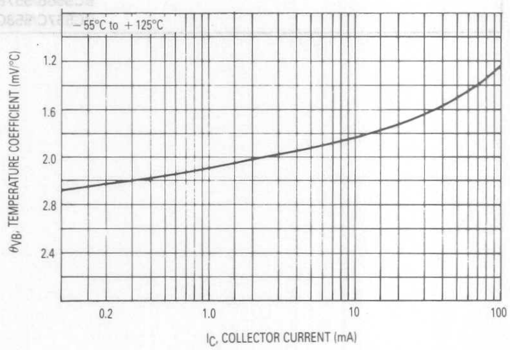


FIGURE 5 – CAPACITANCES

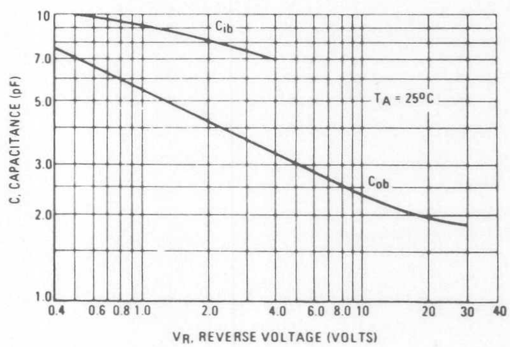
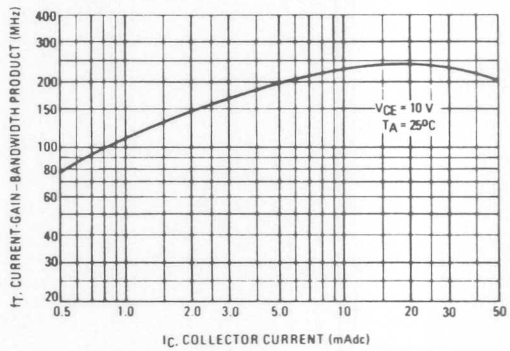


FIGURE 6 – CURRENT GAIN–BANDWIDTH PRODUCT



BC556

FIGURE 7 – DC CURRENT GAIN

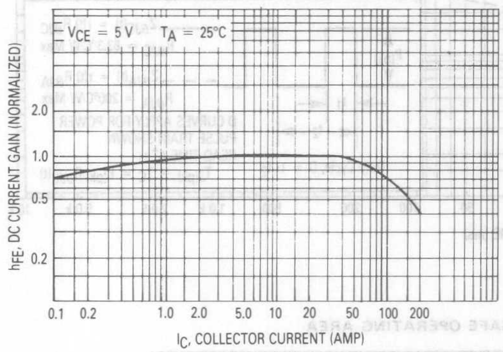


FIGURE 8 – "ON" VOLTAGE

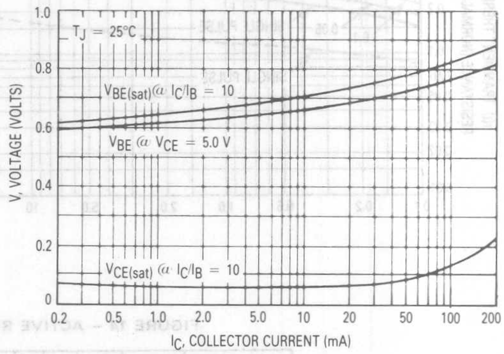


FIGURE 9 – COLLECTOR SATURATION REGION

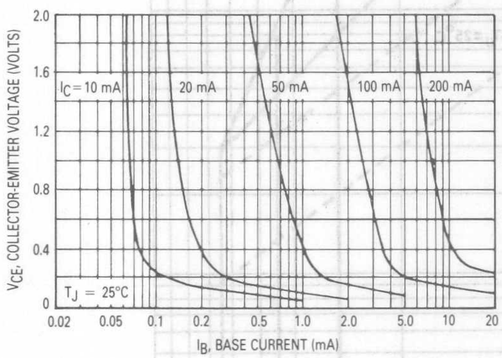


FIGURE 10 – BASE EMITTER TEMPERATURE COEFFICIENT

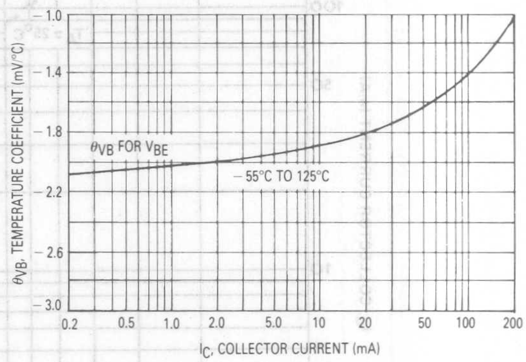


FIGURE 11 – CAPACITANCE

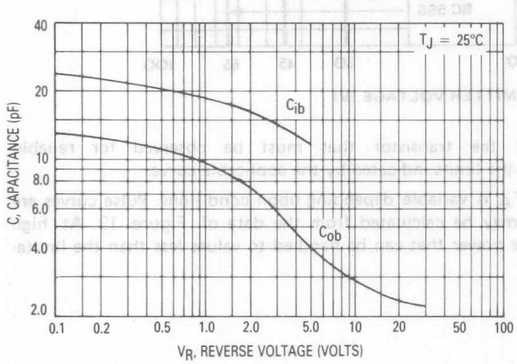
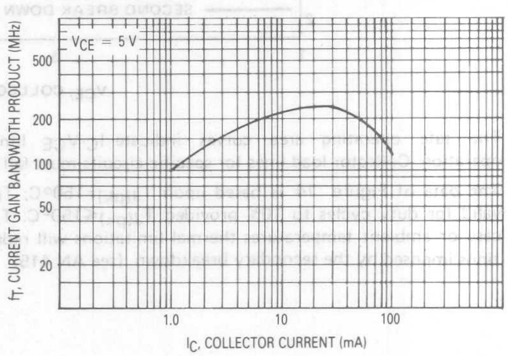


FIGURE 12 – CURRENT GAIN–BANDWIDTH PRODUCT



2

FIGURE 13 – THERMAL RESPONSE

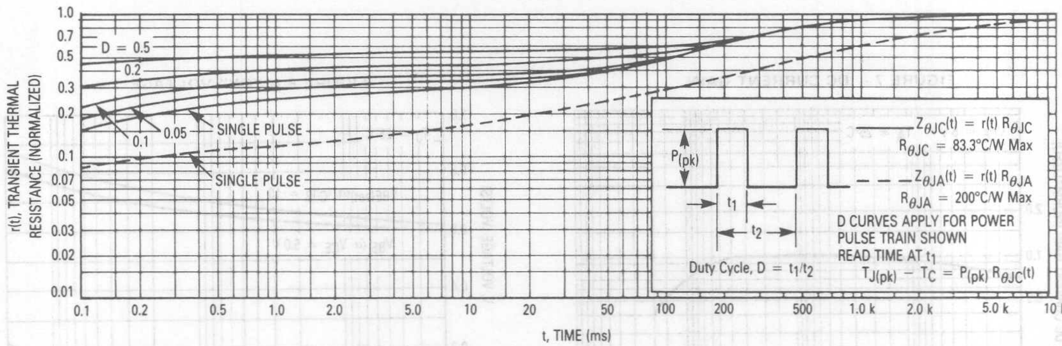
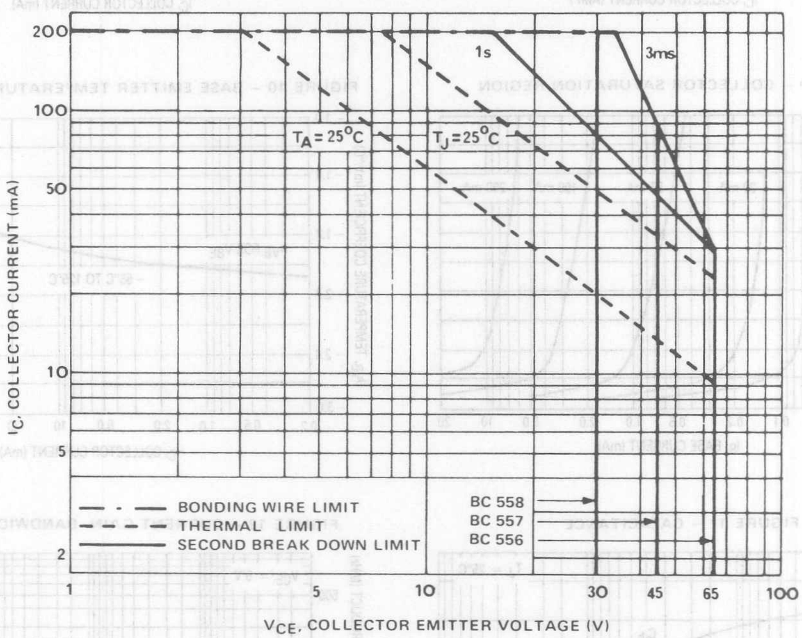


FIGURE 14 – ACTIVE REGION SAFE OPERATING AREA

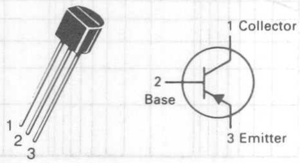


The safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $T_{J(pk)} = 150°C$; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150°C$. $T_{J(pk)}$ may be calculated from the data of Figure 13. At high case or ambient temperatures thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown. (see AN 415).

BC559,B,C
BC560,B,C

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



LOW NOISE TRANSISTORS

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	BC 559	BC 560	Unit
Collector-Emitter Voltage	V_{CEO}	30	45	Vdc
Collector-Base Voltage	V_{CBO}	30	50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current – Continuous	I_C	100		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0) BC559 BC560	$V_{(BR)CEO}$	 30 45			Vdc
Collector-Base Breakdown Voltage (I_C = 10 µAdc, I_E = 0) BC559 BC560	$V_{(BR)CBO}$	 30 50			Vdc
Emitter-Base Breakdown Voltage (I_E = 10 µAdc, I_C = 0)	$V_{(BR)EBO}$	 5			Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0) (V_{CB} = 30 Vdc, I_E = 0, T_A = +125°C)	I_{CBO}			 15 5	 nAdc µAdc
Emitter Cutoff Current (V_{EB} = 4 Vdc, I_C = 0)	I_{EBO}			 15	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 10 µAdc, V_{CE} = 5 Vdc) BC559B/560B BC559C/560C (I_C = 2 mAdc, V_{CE} = 5 Vdc) BC559B/560B BC559C/560C BC559/560	h_{FE}	 100 100 180 380 120	 150 270 290 500	 460 800 800	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.5 mAdc) (I_C = 10 mAdc, I_B = see note 1) (I_C = 100 mAdc, I_B = 5 mAdc, see note 2)	$V_{CE(sat)}$		 0.075 0.3 0.25	 0.25 0.6	Vdc
Base-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 5 mAdc)	$V_{BE(sat)}$		 1.1		Vdc
Base-Emitter On Voltage (I_C = 10 µAdc, V_{CE} = 5 Vdc) (I_C = 100 µAdc, V_{CE} = 5 Vdc) (I_C = 2 mAdc, V_{CE} = 5 Vdc)	$V_{BE(on)}$	 0.55	 0.52 0.55 0.62	 0.7	Vdc
SMALL SIGNAL CHARACTERISTICS					
Current-Gain-Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5 Vdc, f = 100 MHz)	f_T		 250		MHz
Collector-Base Capacitance (V_{CE} = 10 Vdc, I_E = 0, f = 1 MHz)	C_{cbo}		 2.5		pF
Small-Signal Current Gain (I_C = 2.0 mAdc, V_{CE} = 5.0 V, f = 1.0 kHz) BC559B/BC560B BC559C/BC560C	h_{fe}	 240 450	 330 600	 500 900	—
Noise Figure (I_C = 200 µAdc, V_{CE} = 5.0 Vdc, R_S = 2.0 kΩ, f = 30 Hz–15 kHz) (I_C = 200 µA, V_{CE} = 5.0 V, R_S = 100 kΩ, f = 1.0 kHz, Δf = 200 Hz)	 NF_1 NF_2	 — —	 0.5 —	 2.0 10	dB

Note 1: I_B is value for which I_C = 11 mA at V_{CE} = 1 V

Note 2: Pulse test = 300 µs – Duty cycle = 2%

2

FIGURE 1 — NORMALIZED DC CURRENT GAIN

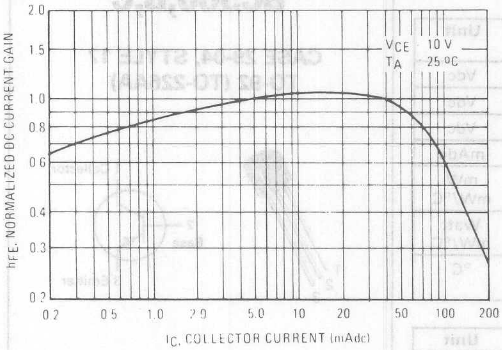


FIGURE 2 — "SATURATION" AND "ON" VOLTAGES

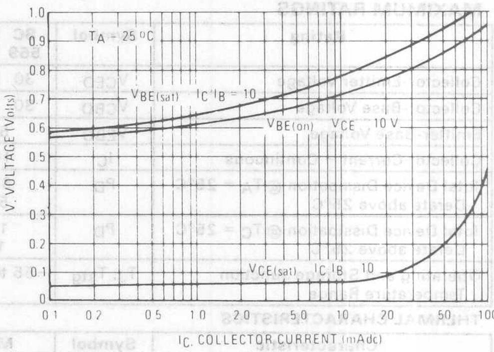


FIGURE 3 — CURRENT-GAIN BANDWIDTH PRODUCT

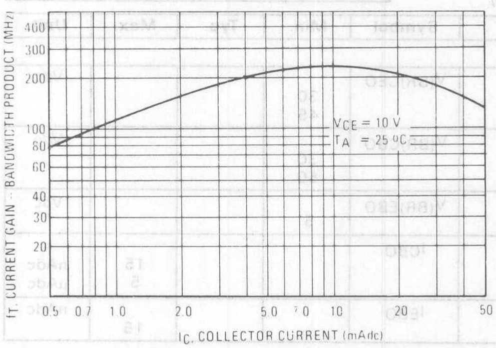


FIGURE 4 — CAPACITANCE

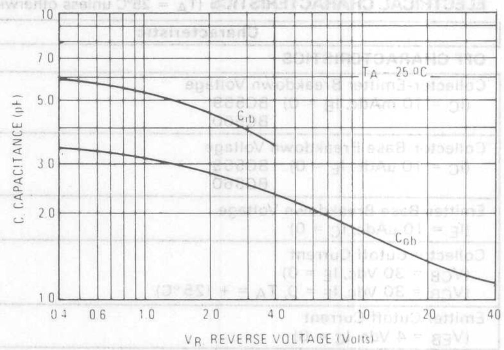
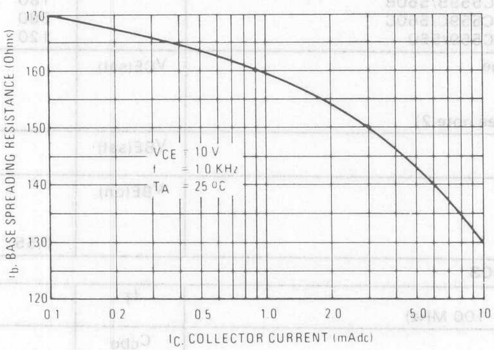
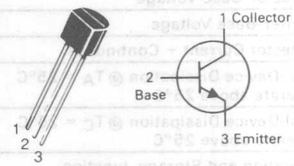


FIGURE 5 — BASE SPREADING RESISTANCE



BC617
BC618

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



DARLINGTON TRANSISTORS

NPN SILICON

Refer to 2N6426 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BC 617	BC 618	Unit
Collector-Emitter Voltage	V_{CEO}	40	55	Vdc
Collector-Base Voltage	V_{CBO}	50	80	Vdc
Emitter-Base Voltage	V_{EBO}	12		Vdc
Collector Current − Continuous	I_C	1.0		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

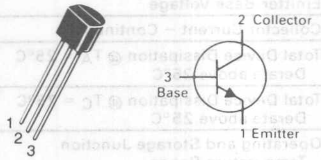
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, V_{BE} = 0)	BC617 BC618	$V_{(BR)CEO}$	40 55	— —	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	BC617 BC618	$V_{(BR)CBO}$	50 80	— —	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	Both Types	$V_{(BR)EBO}$	12	—	—	Vdc
Collector Cutoff Current (V_{CE} = 40 Vdc, V_{BE} = 0) (V_{CE} = 60 Vdc, V_{BE} = 0)	BC617 BC618	I_{CES}	— —	— —	50 50	nAdc
Collector Cutoff Current (V_{CB} = 40 Vdc, I_E = 0) (V_{CB} = 60 Vdc, I_E = 0)	BC617 BC618	I_{CBO}	— —	— —	50 50	nAdc
Emitter Cutoff Current (V_{BE} = 10 Vdc, I_C = 0)	Both Types	I_{EBO}	—	—	50	nAdc
ON CHARACTERISTICS						
Collector-Emitter Saturation Voltage (I_C = 200 mA, I_B = 0.2 mA)	Both Types	$V_{CE(sat)}$	—	—	1.1	Vdc
Base-Emitter Saturation Voltage (I_C = 200 mA, I_B = 0.2 mA)	Both Types	$V_{BE(sat)}$	—	—	1.6	Vdc
Current Gain (I_C = 100 μA, V_{CE} = 5.0 V)	BC617 BC618	h_{FE}	4000 2000	— —	— —	
(I_C = 10 mA, V_{CE} = 5.0 V)	BC617 BC618		10000 4000	— —	— —	
(I_C = 200 mA, V_{CE} = 5.0 V)	BC617 BC618		20000 10000	— —	70000 50000	
(I_C = 1.0 A, V_{CE} = 5.0 V)	BC617 BC618		10000 4000	— —	— —	
DYNAMIC CHARACTERISTICS						
Current-Gain Bandwidth Product (I_C = 500 mA, V_{CE} = 5.0 V, P = 100 MHz)	Both Types	f_T	150	—	—	MHz
Output Capacitance (V_{CB} = 10 V, I_E = 0, f = 1.0 MHz)		C_{ob}	—	4.5	7.0	pF
Input Capacitance (V_{EB} = 5.0 V, I_E = 0, f = 1.0 MHz)		C_{ib}	—	5.0	9.0	pF

BC637
BC639

CASE 29-04, STYLE 14
TO-92 (TO-226AA)



HIGH CURRENT TRANSISTORS

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	BC 635	BC 637	BC 639	Unit
Collector-Emitter Voltage	V_{CEO}	45	60	80	Vdc
Collector-Base Voltage	V_{CBO}	45	60	80	Vdc
Emitter-Base Voltage	V_{EBO}		5.0		Vdc
Collector Current – Continuous	I_C		1.0		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D		800 6.4		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D		2.75 22		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		–55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	45	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	156	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage* ($I_C = 10$ mAdc, $I_B = 0$)	BC635 BC637 BC639	$V_{(BR)CEO}$	45 60 80	— — —	— — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	BC635 BC637 BC639	$V_{(BR)CBO}$	45 60 80	— — —	— — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$, ($V_{CB} = 30$ Vdc, $I_E = 0$, $T_A = 125°C$)		I_{CBO}	— —	— —	100 10	nAdc μAdc
ON CHARACTERISTICS*						
DC Current Gain ($I_C = 5.0$ mAdc, $V_{CE} = 2.0$ Vdc) ($I_C = 150$ mAdc, $V_{CE} = 2.0$ Vdc) ($I_C = 500$ mA, $V_{CE} = 2.0$ V)	 BC635 BC637 BC639	h_{FE}	25 40 40 40 25	— — —	— 250 160 160 —	
Collector-Emitter Saturation Voltage ($I_C = 500$ mAdc, $I_B = 50$ mAdc)		$V_{CE(sat)}$	—	—	0.5	Vdc
Base-Emitter On Voltage ($I_C = 500$ mAdc, $V_{CE} = 2.0$ Vdc)		$V_{BE(on)}$	—	—	1.0	Vdc
DYNAMIC CHARACTERISTICS						
Current-Gain Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 2.0$ Vdc, f = 100 MHz)		f_T	—	200	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{ob}	—	7.0	—	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)		C_{ib}	—	50	—	pF

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle 2.0%.

2

FIG. 1 — ACTIVE REGION SAFE OPERATING AREA

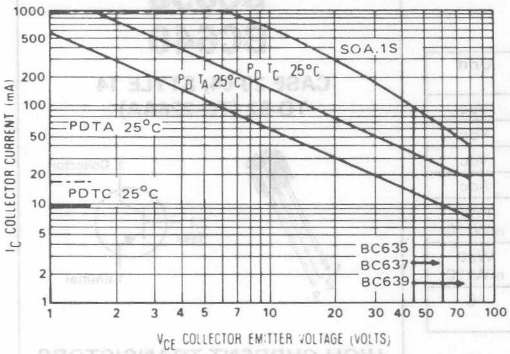


FIG. 2 — DC CURRENT GAIN

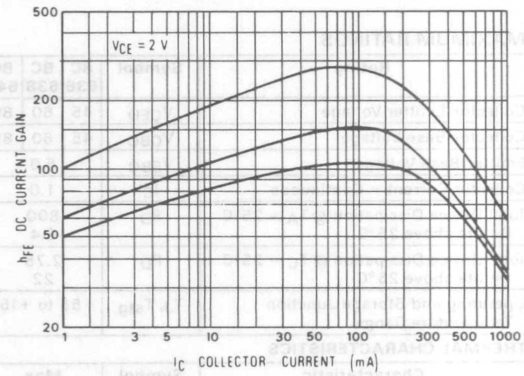


FIG. 3 — CURRENT GAIN BANDWIDTH PRODUCT

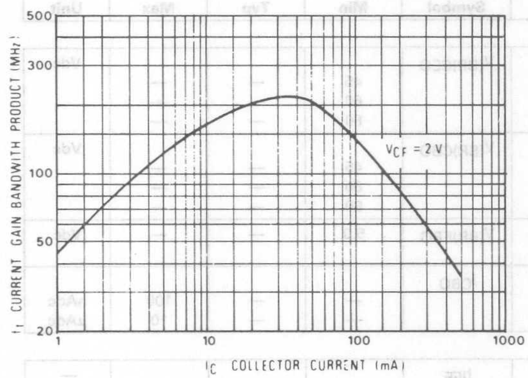


FIG. 4 — "SATURATION" AND "ON" VOLTAGES

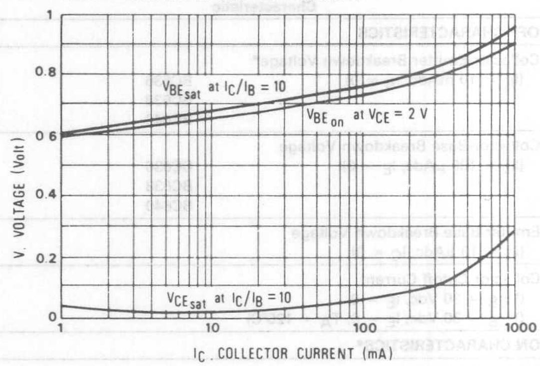
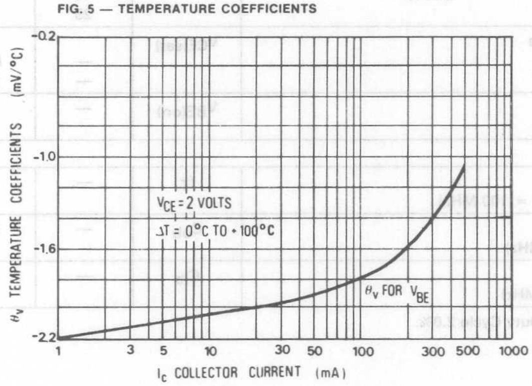
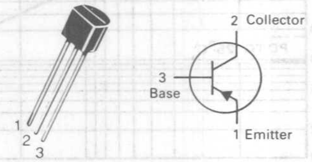


FIG. 5 — TEMPERATURE COEFFICIENTS



BC636
BC638
BC640

CASE 29-04, STYLE 14
TO-92 (TO-226AA)



HIGH CURRENT TRANSISTORS

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	BC 636	BC 638	BC 640	Unit
Collector-Emitter Voltage	V_{CEO}	45	60	80	Vdc
Collector-Base Voltage	V_{CBO}	45	60	80	Vdc
Emitter-Base Voltage	V_{EBO}		5.0		Vdc
Collector Current — Continuous	I_C		1.0		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D		800 6.4		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D		2.75 22		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	45	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	156	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage*		$V_{(BR)CEO}$				Vdc
($I_C = 10$ mAdc, $I_B = 0$)	BC636		45	—	—	
	BC638		60	—	—	
	BC640		80	—	—	
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$				Vdc
($I_C = 100$ μAdc, $I_E = 0$)	BC636		45	—	—	
	BC638		60	—	—	
	BC640		80	—	—	
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current		I_{CBO}				
($V_{CB} = 30$ Vdc, $I_E = 0$,)			—	—	100	nAdc
($V_{CB} = 30$ Vdc, $I_E = 0$, $T_A = 125°C$)			—	—	10	μAdc
ON CHARACTERISTICS*						
DC Current Gain		h_{FE}				—
($I_C = 5.0$ mAdc, $V_{CE} = 2.0$ Vdc)			25	—	—	
($I_C = 150$ mAdc, $V_{CE} = 2.0$ Vdc)	BC636		40	—	250	
	BC638		40	—	160	
	BC640		40	—	160	
($I_C = 500$ mA, $V_{CE} = 2.0$ V)			25	—	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$				Vdc
($I_C = 500$ mAdc, $I_B = 50$ mAdc)			—	0.25	0.5	
			—	0.5	—	
Base-Emitter On Voltage ($I_C = 500$ mAdc, $V_{CE} = 2.0$ Vdc)		$V_{BE(on)}$	—	—	1.0	Vdc
DYNAMIC CHARACTERISTICS						
Current-Gain Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 2.0$ Vdc, f = 100 MHz)		f_T	—	150	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{ob}	—	9.0	—	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)		C_{ib}	—	110	—	pF

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle 2.0%.

FIG. 1 — ACTIVE REGION SAFE OPERATING AREA

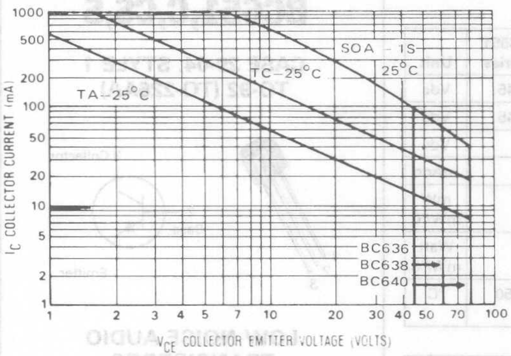


FIG. 2 — DC CURRENT GAIN

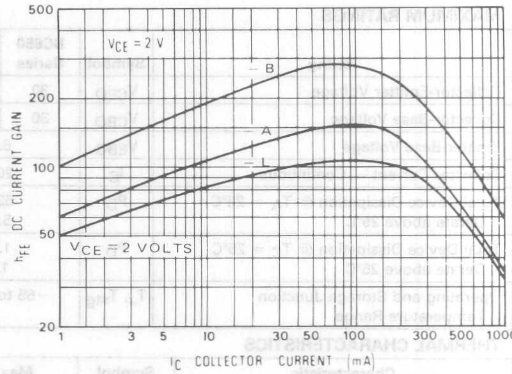


FIG. 3 — CURRENT GAIN BANDWIDTH PRODUCT

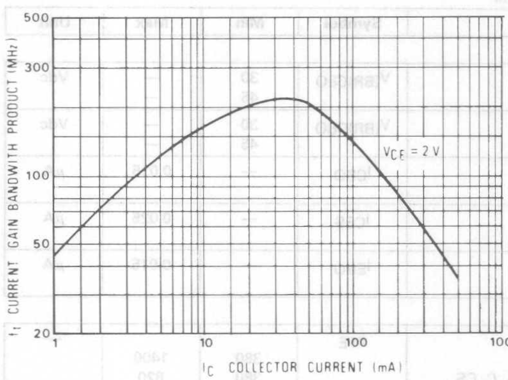


FIG. 4 — "SATURATION" AND "ON" VOLTAGES

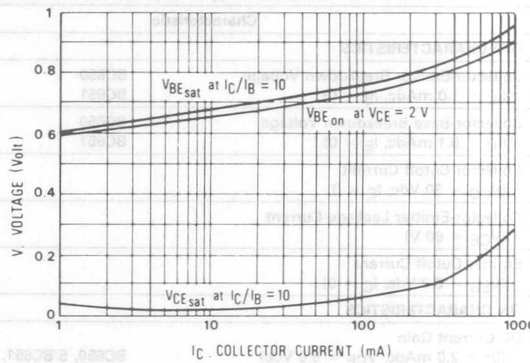
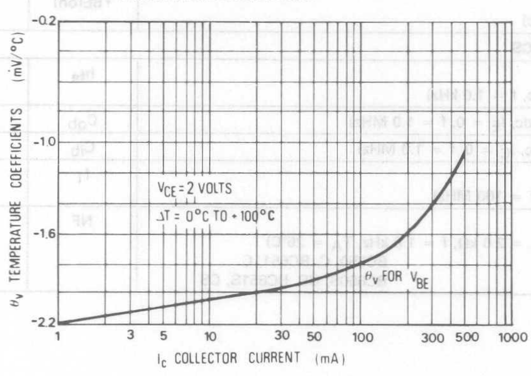


FIG. 5 — TEMPERATURE COEFFICIENTS

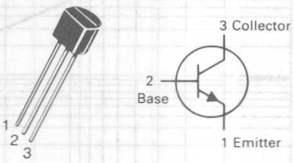


Rating	Symbol	BC650 Series	BC651 Series	Unit
Collector-Emitter Voltage	V_{CEO}	30	45	Vdc
Collector-Base Voltage	V_{CBO}	30	45	Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



LOW NOISE AUDIO TRANSISTORS

NPN SILICON

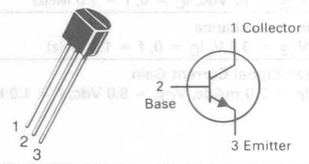
Refer to MPSA18 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	BC650 BC651	$V_{(BR)CEO}$	30 45	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 0.1 mAdc, I_E = 0)	BC650 BC651	$V_{(BR)CBO}$	30 45	— —	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)		I_{CBO}	—	0.015	μA
Collector-Emitter Leakage Current (V_{CE} = 60 V)		I_{CES}	—	0.025	μA
Emitter Cutoff Current (V_{EB} = 6.0 Vdc, I_C = 0)		I_{EBO}	—	0.015	μA
ON CHARACTERISTICS					
DC Current Gain (I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)	BC650, S/BC651, S BC650, C, CS/BC651, C, CS	h_{FE}	380 380	1400 820	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.5 mAdc) (I_C = 100 mAdc, I_B = 5.0 mAdc)		$V_{CE(sat)}$	— —	0.2 0.6	Vdc
Base Emitter On Voltage (I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)		$V_{BE(on)}$	0.55	0.7	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Small-Signal Current Gain (I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)		h_{fe}	380	1600	—
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{ob}	—	3.0	pF
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{ib}	—	8.0	pF
Current-Gain Bandwidth Product (I_C = 1.0 mAdc, V_{CE} = 5.0 V, f = 100 MHz)		f_T	100	700	MHz
Noise Figure (V_{CE} = 5.0 V, I_C = 0.2 mA, R_S = 2.0 kΩ, f = 1.0 kHz, T_A = 25°C)	BC650, C, BC651, C BC650S, CS, BC651S, CS	NF	— —	2.8 2.0	dB

BCX58,-7,-8,-9,-10
BCX59,-7,-8,-9,-10

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

NPN SILICON

2

MAXIMUM RATINGS

Rating	Symbol	BCX 58	BCX 59	Unit
Collector-Emitter Voltage	V_{CEO}	32	45	Vdc
Collector-Base Voltage	V_{CBO}	32	45	Vdc
Emitter-Base Voltage	V_{EBO}	7.0		Vdc
Collector Current – Continuous	I_C	100		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage ($I_C = 10$ mAdc, $I_B = 0$)	BCX58 BCX59	$V_{(BR)CEO}$	32 45	— —	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 1.0$ μAdc, $I_C = 0$)	All	$V_{(BR)EBO}$	7.0	8.7	—	Vdc
Collector Cutoff Current ($V_{CE} = 32$ V) ($V_{CE} = 45$ V) ($V_{CE} = 32$ V, $T_A = 100°C$, $V_{BE} = 0.2$ V) ($V_{CE} = 45$ V, $T_A = 100°C$, $V_{BE} = 0.2$ V) ($V_{CE} = 32$ V, $T_A = 125°C$) ($V_{CE} = 45$ V, $T_A = 125°C$)	BCX58 BCX59 BCX58 BCX59 BCX58 BCX59	I_{CES} I_{CES} I_{CEX} I_{CEX} I_{CES} I_{CES}	— — — — — —	— — — — — —	10 10 20 20 2.5 2.5	nAdc μAdc
Emitter-Cutoff Current ($V_{EBO} = 4.0$ V, $I_C = 0$)		I_{EBO}	—	—	20	nAdc
ON CHARACTERISTICS						
DC Current Gain ($I_C = 10$ μAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 2.0$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 2.0$ Vdc)	 BCX58-7, BCX59-7 BCX58-8, BCX59-8 BCX58-9, BCX59-9 BCX58-10, BCX59-10 BCX58-7, BCX59-7 BCX58-8, BCX59-8 BCX58-9, BCX59-9 BCX58-10, BCX59-10 BCX58-7, BCX59-7 BCX58-8, BCX59-8 BCX58-9, BCX59-9 BCX58-10, BCX59-10 BCX58-7, BCX59-7 BCX58-8, BCX59-8 BCX58-9, BCX59-9 BCX58-10, BCX59-10	h_{FE}	 20 40 75 100 120 180 250 380 80 120 160 240 40 45 60 60	 80 145 220 300 170 250 350 500 190 260 380 550 — — — —	 — — — — 220 310 460 630 — 400 630 1000 — — — —	—
Collector-Emitter Saturation Voltage ($I_C = 100$ mAdc, $I_B = 5.0$ mAdc)		$V_{CE(sat)}$	—	—	0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 100$ mA, $I_B = 2.5$ mAdc)		$V_{BE(sat)}$	—	—	1.0	Vdc
Base-Emitter On Voltage ($I_C = 2.0$ mAdc, $V_{CE} = 5.0$ Vdc)		$V_{BE(on)}$	0.55	—	0.7	Vdc

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5.0 V, f = 100 MHz)		f_T	125	250	—	MHz
Output Capacitance (V_{CE} = 10 Vdc, I_C = 0, f = 1.0 MHz)		C_{ob}	—	1.8	4.5	pF
Input Capacitance (V_{BE} = 0.5 V, I_C = 0, f = 1.0 MHz)		C_{ib}	—	5.2	15	pF
Small-Signal Current Gain (I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	BCX58-7, BCX59-7	h_{fe}	125	—	250	—
	BCX58-8, BCX59-8		175	—	350	
	BCX58-9, BCX59-9		250	—	500	
	BCX58-10, BCX59-10		350	—	700	
Noise Figure (I_C = 0.2 mAdc, V_{CE} = 5.0 Vdc, R_S = 2.0 kohms, f = 1.0 kHz)		NF	—	1.0	6.0	dB
(I_C = 10 mA, I_{B1} = 1.0 mA, I_{B2} = 1.0 mA) (V_{BB} = 3.6 V, R_1 = R_2 = 5.0 kΩ) (R_L = 999 ohms)		T_d	—	16	—	ns
		T_r	—	29	—	
		T_{on}	—	45	150	
*See test circuit		T_s	—	475	—	
		T_f	—	40	—	
		T_{off}	—	515	800	
(I_C = 100 mA, I_{B1} = 10 mA, I_{B2} = 10 mA) (V_{BB} = 5.0 V, R_1 = 500 Ω, R_2 = 700 Ω) (R_L = 98 ohms)		t_d	—	5.0	—	ns
		t_r	—	40	—	
		t_{on}	—	45	150	
*See test circuit		t_s	—	135	—	
		t_f	—	80	—	
		t_{off}	—	215	800	

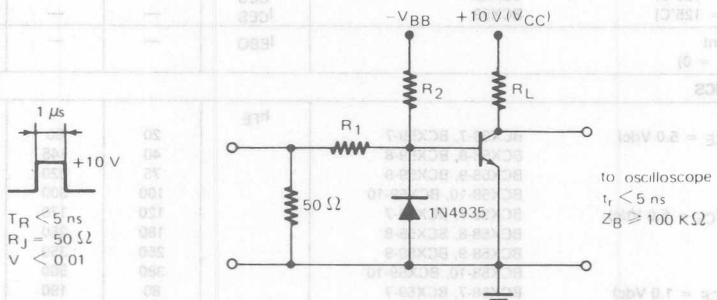


FIGURE 1 – NORMALIZED DC CURRENT GAIN

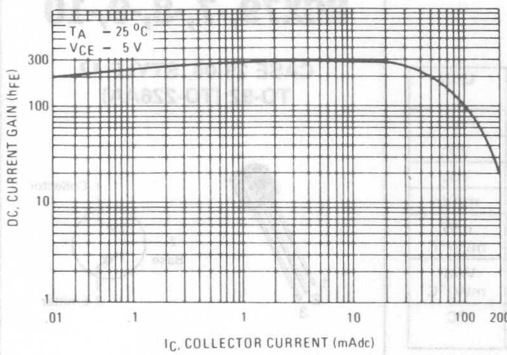


FIGURE 2 – "SATURATION" AND "ON" VOLTAGES

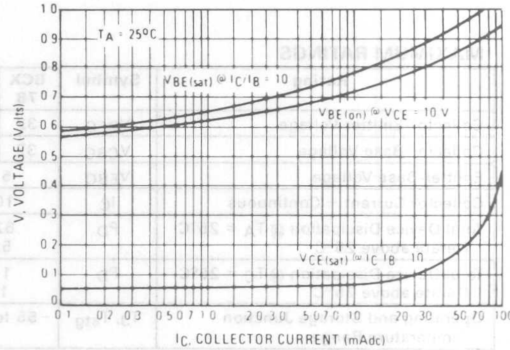


FIGURE 3 – COLLECTOR SATURATION REGION

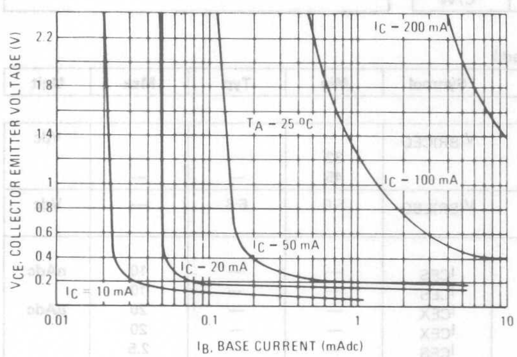


FIGURE 4 – BASE-EMITTER TEMPERATURE COEFFICIENT

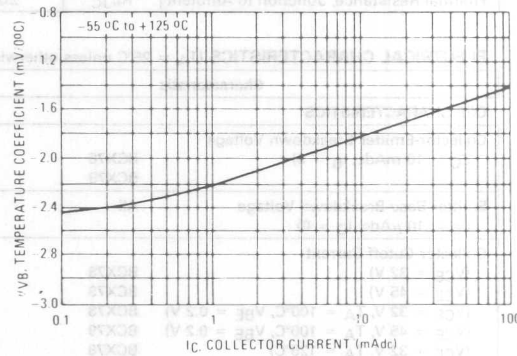


FIGURE 5 – CAPACITANCES

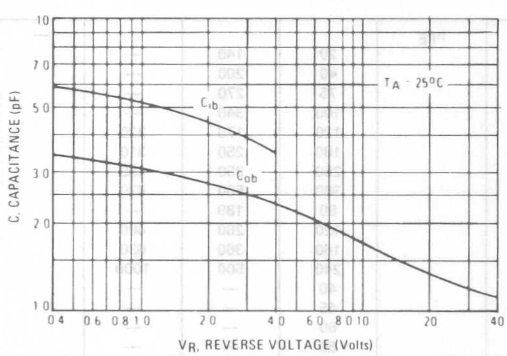
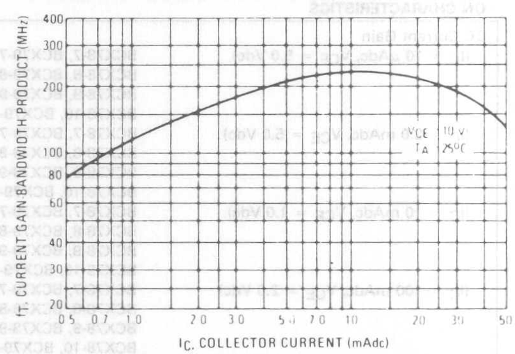
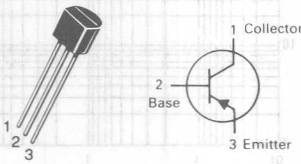


FIGURE 6 – CURRENT-GAIN-BANDWIDTH PRODUCT



BCX78,-7,-8,-9,-10
BCX79,-7,-8,-9,-10

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	BCX 78	BCX 79	Unit
Collector-Emitter Voltage	V_{CEO}	32	45	Vdc
Collector-Base Voltage	V_{CBO}	32	45	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current – Continuous	I_C	100		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

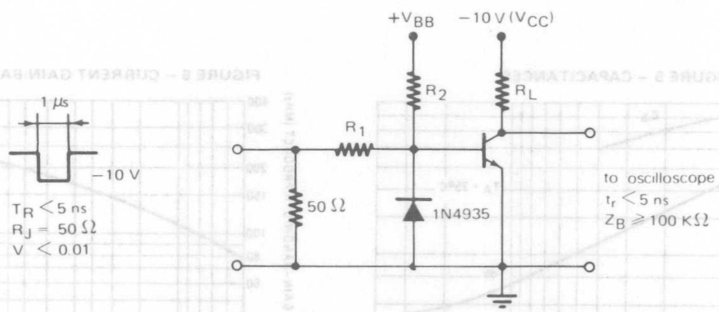
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	 BCX78 BCX79	$V_{(BR)CEO}$	 32 45	 — —	 — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	All	$V_{(BR)EBO}$	5.0	6.8	—	Vdc
Collector Cutoff Current (V_{CE} = 32 V) (V_{CE} = 45 V) (V_{CE} = 32 V, T_A = 100°C, V_{BE} = 0.2 V) (V_{CE} = 45 V, T_A = 100°C, V_{BE} = 0.2 V) (V_{CE} = 32 V, T_A = 125°C) (V_{CE} = 45 V, T_A = 125°C)	 BCX78 BCX79 BCX78 BCX79 BCX78 BCX79	 I_{CES} I_{CES} I_{CEX} I_{CEX} I_{CES} I_{CES}	 — — — — — —	 — — — — — —	 10 10 20 20 2.5 2.5	 nAdc μAdc
Emitter-Cutoff Current (V_{EBO} = 4.0 V, I_C = 0)		I_{EBO}	—	—	20	nAdc
ON CHARACTERISTICS						
DC Current Gain		h_{FE}				—
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc)	BCX78-7, BCX79-7 BCX78-8, BCX79-8 BCX78-9, BCX79-9 BCX78-10, BCX79-10		20 40 75 100	140 200 270 340	— — — —	
(I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)	BCX78-7, BCX79-7 BCX78-8, BCX79-8 BCX78-9, BCX79-9 BCX78-10, BCX79-10		120 180 250 380	170 250 350 500	220 310 460 630	
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	BCX78-7, BCX79-7 BCX78-8, BCX79-8 BCX78-9, BCX79-9 BCX78-10, BCX79-10		80 120 160 240	180 260 360 500	— 400 630 1000	
(I_C = 100 mAdc, V_{CE} = 2.0 Vdc)	BCX78-7, BCX79-7 BCX78-8, BCX79-8 BCX78-9, BCX79-9 BCX78-10, BCX79-10		40 45 60 60	— — — —	— — — —	
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 5.0 mAdc)		$V_{CE(sat)}$	—	—	0.6	Vdc
Base-Emitter Saturation Voltage (I_C = 100 mA, I_B = 5.0 mAdc)		$V_{BE(sat)}$	—	—	1.0	Vdc
Base-Emitter On Voltage (I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)		$V_{BE(on)}$	0.55	—	0.7	Vdc

Characteristic		Symbol	Min	Typ	Max	Unit
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5.0 V, f = 100 MHz)		f_T	—	200	—	MHz
Output Capacitance (V_{CE} = 10 Vdc, I_C = 0, f = 1.0 MHz)		C_{ob}	—	2.6	4.5	pF
Input Capacitance (V_{BE} = 0.5 V, I_C = 0, f = 1.0 MHz)		C_{ib}	—	8.5	15	pF
Small-Signal Current Gain		h_{fe}				—
(I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	BCX78-7, BCX79-7		125	200	250	
	BCX78-8, BCX79-8		175	260	350	
	BCX78-9, BCX79-9		250	330	500	
	BCX78-10, BCX79-10		350	520	700	
Noise Figure (I_C = 0.2 mAdc, V_{CE} = 5.0 Vdc, R_g = 2.0 kohms, f = 1.0 kHz)		NF	—	1.0	6.0	dB
(I_C = 10 mA, I_{B1} = 1.0 mA, I_{B2} = 1.0 mA) (V_{BB} = 3.6 V, R_1 = R_2 = 5.0 kΩ) (R_L = 999 ohms)		T_d	—	17	—	nS
		T_r	—	27	—	
		T_{on}	—	44	150	
*See test circuit		T_s	—	400	—	
		T_f	—	60	—	
		T_{off}	—	460	800	
(I_C = 100 mA, I_{B1} = 10 mA, I_{B2} = 10 mA) (V_{BB} = 5.0 V, R_1 = 500 Ω, R_2 = 700 Ω) (R_L = 98 ohms)		t_d	—	5.0	—	ns
		t_r	—	20	—	
		t_{on}	—	25	150	
*See test circuit		t_s	—	130	—	
		t_f	—	40	—	
		t_{off}	—	170	800	

TEST CIRCUIT



2

FIGURE 1 – NORMALIZED DC CURRENT GAIN

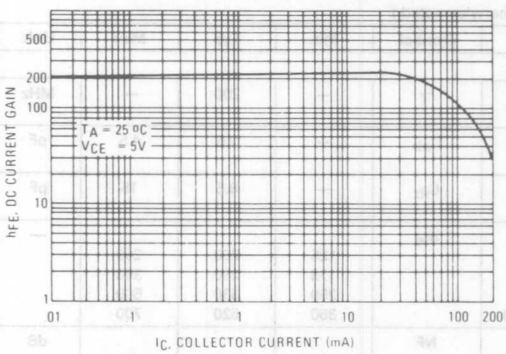


FIGURE 2 – "SATURATION" AND "ON" VOLTAGES

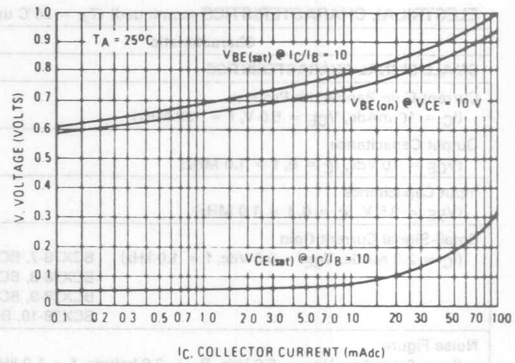


FIGURE 3 – COLLECTOR SATURATION REGION

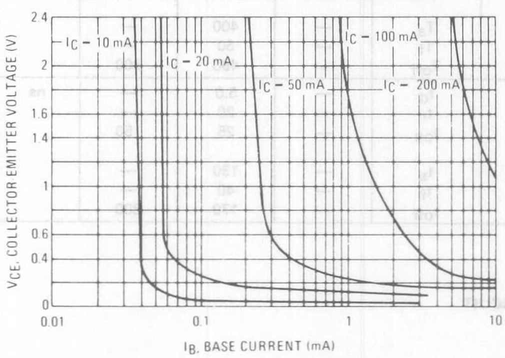


FIGURE 4 – BASE EMITTER TEMPERATURE COEFFICIENT

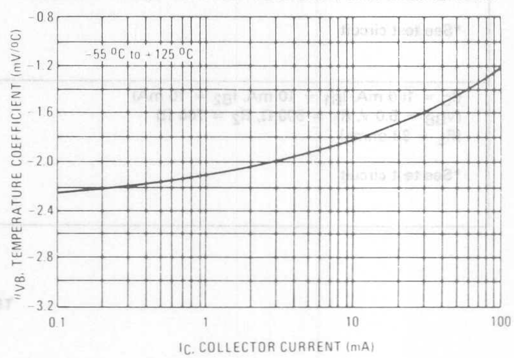


FIGURE 5 – CAPACITANCES

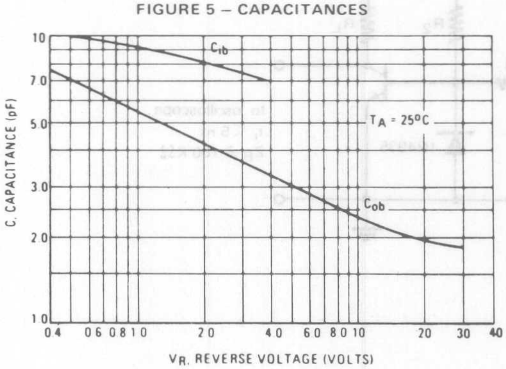
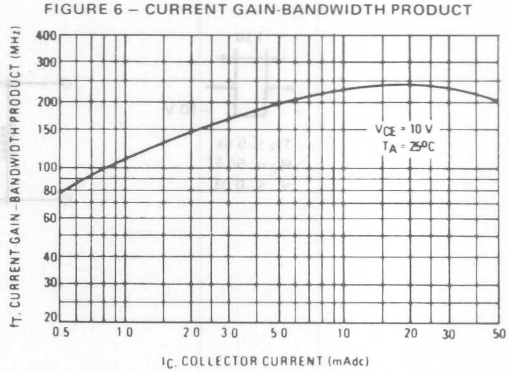
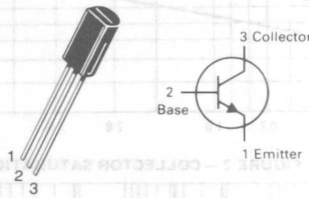


FIGURE 6 – CURRENT GAIN-BANDWIDTH PRODUCT



BDB01A Thru BDB01D

CASE 29-03, STYLE 1
TO-92 (TO-226AE)



ONE WATT AMPLIFIER TRANSISTORS

NPN SILICON

2

MAXIMUM RATINGS

Rating	Symbol	BDB 01A	BDB 01B	BDB 01C	BDB 01D	Unit
Collector-Emitter Voltage	V_{CEO}	45	60	80	100	Vdc
Collector-Base Voltage	V_{CES}	45	60	80	100	Vdc
Emitter-Base Voltage	V_{EBO}	5.0				Vdc
Collector Current – Continuous	I_C	0.5				Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.0 8.0				Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	2.5 20				Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150				°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	125	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Voltage (I_C = 10 mA, I_B = 0)	$V_{(BR)CEO}$			Vdc
BDB01A		45		
BDB01B		60		
BDB01C		80		
BDB01D		100		
Collector Cutoff Current	I_{CBO}			μAdc
(V_{CB} = 45 V, I_E = 0) BDB01A			0.1	
(V_{CB} = 60 V, I_E = 0) BDB01B			0.1	
(V_{CB} = 80 V, I_E = 0) BDB01C			0.1	
(V_{CB} = 100 V, I_E = 0) BDB01D			0.1	
Emitter Cutoff Current (I_C = 0, V_{EB} = 5.0 V)	I_{EBO}		100	nAdc
ON CHARACTERISTICS				
DC Current Gain	h_{FE}			
(I_C = 100 mA, V_{CE} = 1 V)		40	400	
(I_C = 500 mA, V_{CE} = 2 V)		25		
Collector-Emitter Saturation Voltage (I_C = 1000 mA, I_B = 100 mA)	$V_{CE(sat)}$		0.7	Vdc
Collector-Emitter on Voltage (I_C = 1000 mA, V_{CE} = 1 V)	$V_{BE(on)}$		1.2	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain Bandwidth Product (I_C = 200 mA, V_{CE} = 5 V, f = 100 MHz)	f_T	50		MHz
Output Capacitance (V_{CB} = 10 V, I_E = 0, f = 1 MHz)	C_{ob}		30	pF

2

FIGURE 1 – D.C. CURRENT GAIN

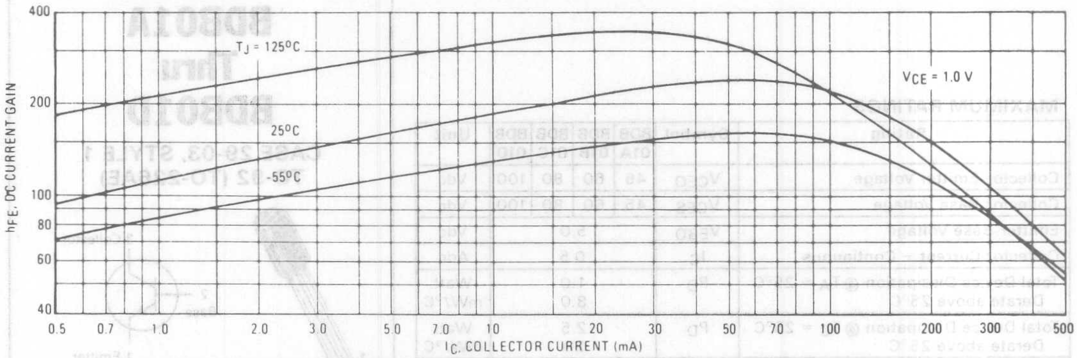


FIGURE 2 – COLLECTOR SATURATION REGION

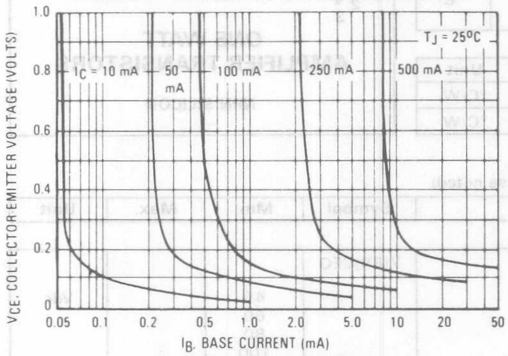


FIGURE 3 – ON VOLTAGES

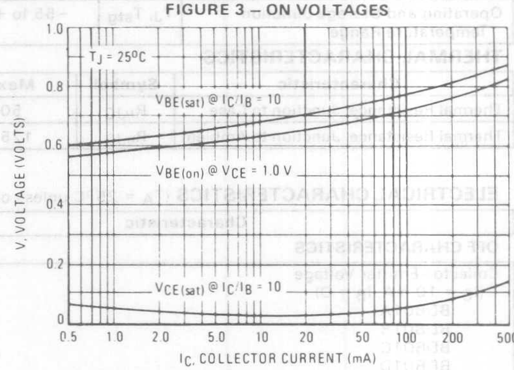


FIGURE 4 – BASE-EMITTER TEMPERATURE COEFFICIENT

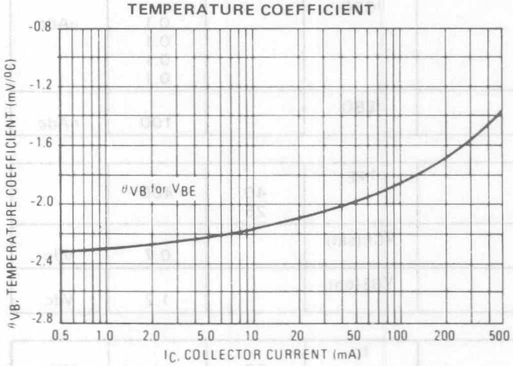


FIGURE 5 – CAPACITANCE

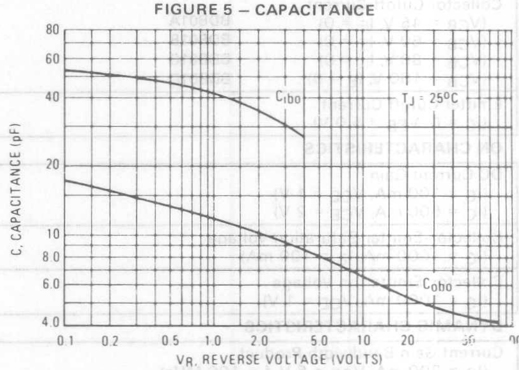


FIGURE 6 – CURRENT GAIN-BANDWIDTH PRODUCT

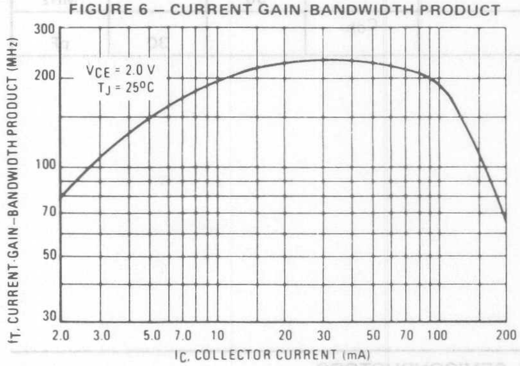
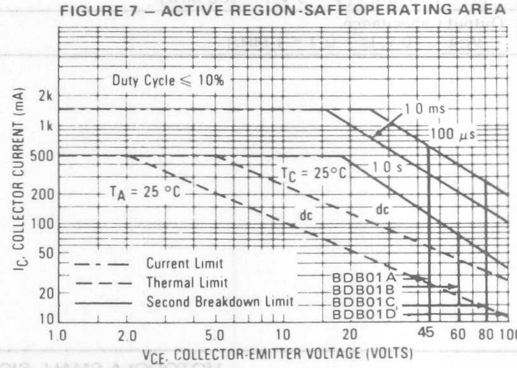
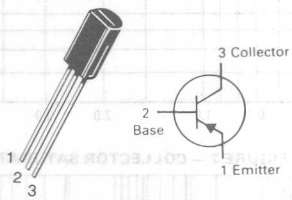


FIGURE 7 – ACTIVE REGION-SAFE OPERATING AREA



BDB02A Thru BDB02D

CASE 29-03, STYLE 1
TO-92 (TO-226AE)



ONE WATT AMPLIFIER TRANSISTORS

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	BDB 02A	BDB 02B	BDB 02C	BDB 02D	Unit
Collector-Emitter Voltage	V_{CEO}	45	60	80	100	Vdc
Collector-Base Voltage	V_{CES}	45	60	80	100	Vdc
Emitter-Base Voltage	V_{EBO}	5.0				Vdc
Collector Current − Continuous	I_C	0.5				Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 8.0				Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 20				Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150				°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	125	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted)

Characteristic	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Voltage ($I_C = 10$ mA, $I_B = 0$) BDB02A	$V_{(BR)CEO}$	45		Vdc
BDB02B		60		
BDB02C		80		
BDB02D		100		
Collector Cutoff Current ($V_{CB} = 45$ V, $I_E = 0$) BDB02A	I_{CBO}		0.1	μAdc
($V_{CB} = 60$ V, $I_E = 0$) BDB02B			0.1	
($V_{CB} = 80$ V, $I_E = 0$) BDB02C			0.1	
($V_{CB} = 100$ V, $I_E = 0$) BDB02D			0.1	
Emitter Cutoff Current ($I_C = 0$, $V_{EB} = 5.0$ V)	I_{EBO}		100	nAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 100$ mA, $V_{CE} = 1$ V)	h_{FE}	40	400	
($I_C = 500$ mA, $V_{CE} = 2$ V)		25		
Collector-Emitter Saturation Voltage ($I_C = 1000$ mA, $I_B = 100$ mA)	$V_{CE(sat)}$		0.7	Vdc
Collector-Emitter on Voltage ($I_C = 1000$ mA, $V_{CE} = 1$ V)	$V_{BE(on)}$		1.2	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain Bandwidth Product ($I_C = 200$ mA, $V_{CE} = 5$ V, f = 100 MHz)	f_T	50		MHz
Output Capacitance ($V_{CB} = 10$ V, $I_E = 0$, f = 1 MHz)	C_{ob}		30	pF

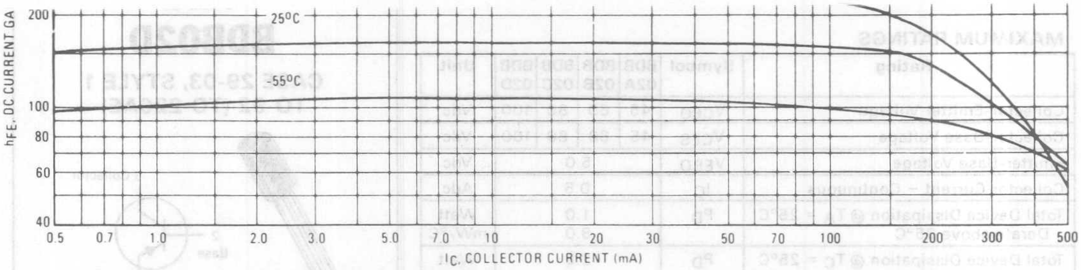


FIGURE 2 — COLLECTOR SATURATION REGION

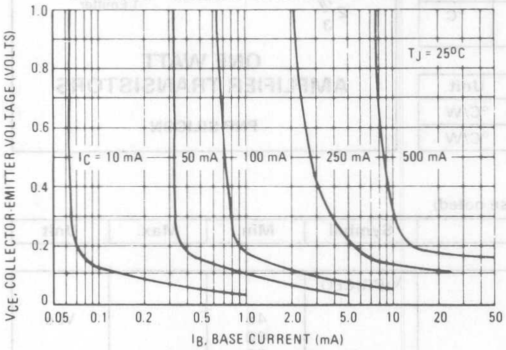


FIGURE 3 — ON VOLTAGES

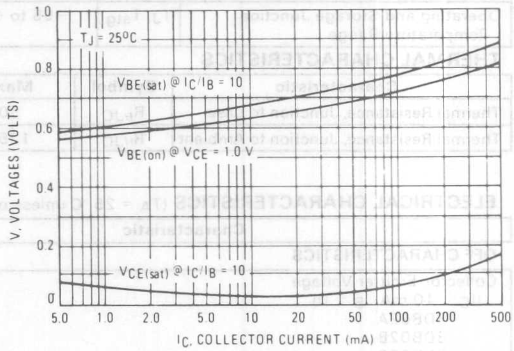


FIGURE 4 — BASE-EMITTER TEMPERATURE COEFFICIENT

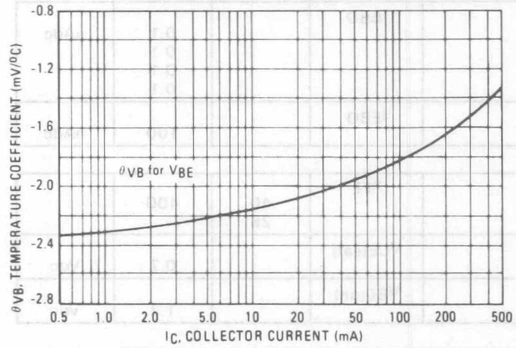


FIGURE 5 — CAPACITANCE

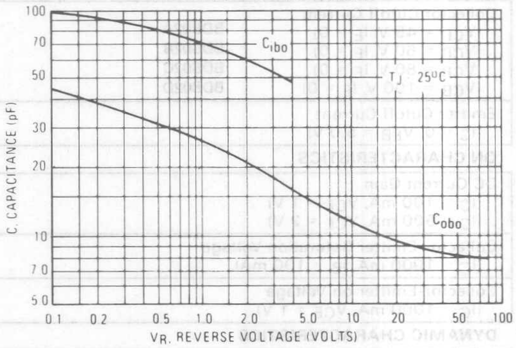


FIGURE 6 — CURRENT GAIN-BANDWIDTH PRODUCT

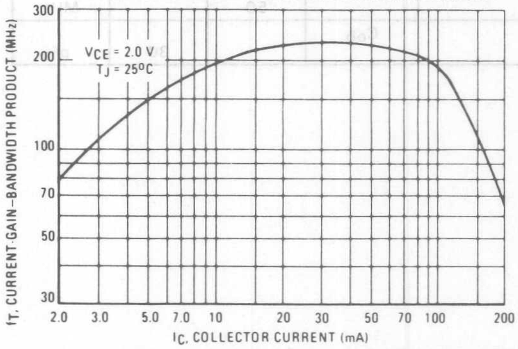
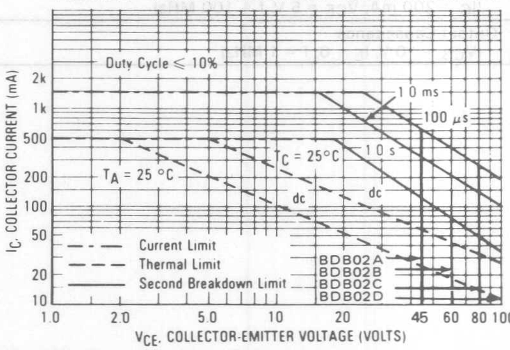
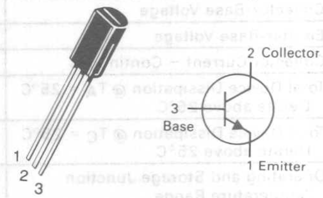


FIGURE 7 — ACTIVE REGION SAFE OPERATING AREA



BDC01A Thru BDC01D

CASE 29-03, STYLE 14
TO-92 (TO-226AE)



ONE WATT AMPLIFIER TRANSISTORS

NPN SILICON

Refer to BDB01A for graphs.

MAXIMUM RATINGS

Rating	Symbol	BDC 01A	BDC 01B	BDC 01C	BDC 01D	Unit
Collector-Emitter Voltage	V_{CEO}	45	60	80	100	Vdc
Collector-Base Voltage	V_{CBO}	45	60	80	100	Vdc
Emitter-Base Voltage	V_{EBO}	5.0				Vdc
Collector Current − Continuous	I_C	1.5				Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 8.0				Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 20				Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150				°C

THERMAL CHARACTERISTICS

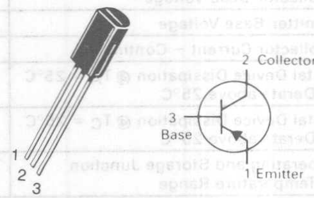
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	125	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted)

Characteristic	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Voltage ($I_C = 10$ mA, $I_B = 0$)	$V_{(BR)CEO}$			Vdc
BDC01A		45		
BDC01B		60		
BDC01C		80		
BDC01D		100		
Collector Cutoff Current	I_{CBO}			μAdc
($V_{CB} = 45$ V, $I_E = 0$) BDC01A			0.1	
($V_{CB} = 60$ V, $I_E = 0$) BDC01B			0.1	
($V_{CB} = 80$ V, $I_E = 0$) BDC01C			0.1	
($V_{CB} = 100$ V, $I_E = 0$) BDC01D			0.1	
Emitter Cutoff Current ($I_C = 0$, $V_{EB} = 5.0$ V)	I_{EBO}		100	nAdc
ON CHARACTERISTICS				
DC Current Gain	h_{FE}			
($I_C = 100$ mA, $V_{CE} = 1$ V)		40	400	
($I_C = 500$ mA, $V_{CE} = 2$ V)		25		
Collector-Emitter Saturation Voltage ($I_C = 1000$ mA, $I_B = 100$ mA)	$V_{CE(sat)}$		0.7	Vdc
Collector-Emitter on Voltage ($I_C = 1000$ mA, $V_{CE} = 1$ V)	$V_{BE(on)}$		1.2	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain Bandwidth Product ($I_C = 200$ mA, $V_{CE} = 5$ V, f = 100 MHz)	f_T	50		MHz
Output Capacitance ($V_{CB} = 10$ V, $I_E = 0$, f = 1 MHz)	C_{ob}		30	pF

BDC02A Thru BDC02D

CASE 29-03, STYLE 14
TO-92 (TO-226AE)



ONE WATT AMPLIFIER TRANSISTORS

PNP SILICON

Refer to BDB02A for graphs.

MAXIMUM RATINGS

Rating	Symbol	BDC 02A	BDC 02B	BDC 02C	BDC 02D	Unit
Collector-Emitter Voltage	V_{CEO}	45	60	80	100	Vdc
Collector-Base Voltage	V_{CBO}	45	60	80	100	Vdc
Emitter-Base Voltage	V_{EBO}		5.0			Vdc
Collector Current − Continuous	I_C		1.5			Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D		1.0 8.0			Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D		2.5 20			Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−55 to +150			°C

THERMAL CHARACTERISTICS

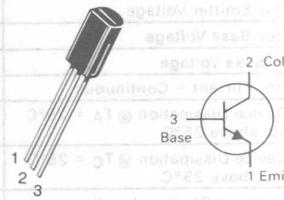
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	125	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Voltage (I_C = 10 mA, I_B = 0) BDC02A BDC02B BDC02C BDC02D	$V_{(BR)CEO}$	 45 60 80 100		Vdc
Collector Cutoff Current (V_{CB} = 45 V, I_E = 0) (V_{CB} = 60 V, I_E = 0) (V_{CB} = 80 V, I_E = 0) (V_{CB} = 100 V, I_E = 0)	I_{CBO}		 0.1 0.1 0.1 0.1	μAdc
Emitter Cutoff Current (I_C = 0, V_{EB} = 5.0 V)	I_{EBO}		100	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 100 mA, V_{CE} = 1 V) (I_C = 500 mA, V_{CE} = 2 V)	h_{FE}	 40 25	 400 	
Collector-Emitter Saturation Voltage (I_C = 1000 mA, I_B = 100 mA)	$V_{CE(sat)}$		0.7	Vdc
Collector-Emitter on Voltage (I_C = 1000 mA, V_{CE} = 1 V)	$V_{BE(on)}$		1.2	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain Bandwidth Product (I_C = 200 mA, V_{CE} = 5 V, f = 100 MHz)	f_T	50		MHz
Output Capacitance (V_{CB} = 10 V, I_E = 0, f = 1 MHz)	C_{ob}		30	pF

BDC07

CASE 29-03, STYLE 14
TO-92 (TO-226AE)



HIGH VOLTAGE TRANSISTORS

NPN SILICON

Refer to MPSW42 for graphs.

2

MAXIMUM RATINGS

Rating	Symbol	BDC 05	BDC 07	Unit
Collector-Emitter Voltage	V_{CEO}	300	250	Vdc
Collector-Base Voltage	V_{CBO}	300	250	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current – Continuous	I_C	500		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1 8.0		Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	2.5 50		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	125	°C/W

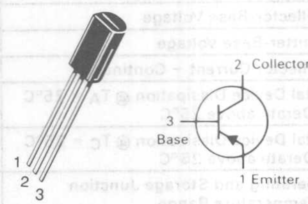
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (1) (I_C = 1 mAdc, I_B = 0)	BDC05 BDC07	$V_{(BR)CEO}$	300 250	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	BDC05 BDC07	$V_{(BR)CBO}$	300 250	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	BDC05 BDC07	$V_{(BR)EBO}$	5.0 5.0	— —	Vdc
Collector Cutoff Current (V_{CB} = 200 Vdc, I_E = 0)	BDC05 BDC07	I_{CBO}	—	0.01	μAdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)	BDC05 BDC07	I_{EBO}	—	10	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 25 mAdc, V_{CE} = 20 Vdc)	BDC05 BDC07	h_{FE}	40 50	— —	—
Collector-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)		$V_{CE(sat)}$		2	Vdc
Base-Emitter Saturation Voltage (I_C = 20 mA, I_B = 2.0 mA)		$V_{BE(sat)}$		2.0	Vdc
DYNAMIC CHARACTERISTICS					
Current Gain–Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 50 MHz)		f_T	60		MHz
Collector-Base Capacitance (V_{CB} = 30 Vdc, I_E = 0, f = 1.0 MHz)		C_{re}		2.8	pF

(1) Pulse Test: Pulse Width ≦ 300 μs, Duty Cycle ≦ 2.0%.

BDC06
BDC08

CASE 29-03, STYLE 14
TO-92 (TO-226AE)



HIGH VOLTAGE TRANSISTORS

PNP SILICON

Refer to MPSW92 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BDC 06	BDC 08	Unit
Collector-Emitter Voltage	V_{CEO}	300	250	Vdc
Collector-Base Voltage	V_{CBO}	300	250	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current – Continuous	I_C	500		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1 8.0		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 20		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	125	°C/W

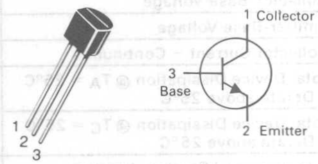
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted)

Characteristic		Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (1) ($I_C = 1$ mAdc, $I_B = 0$)	BDC06 BDC08	$V_{(BR)CEO}$	300 250	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	BDC06 BDC08	$V_{(BR)CBO}$	300 250	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	BDC06 BDC08	$V_{(BR)EBO}$	5.0 5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 200$ Vdc, $I_E = 0$)	BDC06 BDC08	I_{CBO}	—	0.01	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$)	BDC06 BDC08	I_{EBO}	—	10	μAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 25$ mA, $V_{CE} = 20$ Vdc)	BDC06 BDC08	h_{FE}	40 50	— —	—
Collector-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)		$V_{CE(sat)}$		2	Vdc
Base-Emitter Saturation Voltage ($I_C = 20$ mA, $I_B = 2.0$ mA)		$V_{BE(sat)}$		2.0	Vdc
DYNAMIC CHARACTERISTICS					
Current Gain–Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 50 MHz)		f_T	60	—	MHz
Collector-Base Capacitance ($V_{CB} = 30$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{re}		2.8	pF

(1) Pulse Test: Pulse Width ≦ 300 μs, Duty Cycle ≦ 2.0%.

BF199

CASE 29-04, STYLE 21
TO-92 (TO-226AA)



RF TRANSISTOR

NPN SILICON

Refer to BF240 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current − Continuous	I_C	100	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

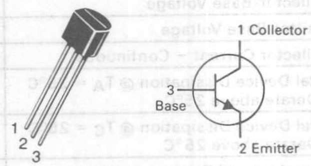
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 1 mAdc, I_B = 0)	$V_{(BR)CEO}$	25			Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	40			Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	4			Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0)	I_{CBO}			100	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 7 mAdc, V_{CE} = 10 Vdc)	h_{FE}	40	85		
Base-Emitter On Voltage (I_C = 7 mAdc, V_{CE} = 10 Vdc)	$V_{BE(on)}$		770	900	mVdc
SMALL-SIGNAL CHARACTERISTICS					
Current Gain−Bandwidth Product (2) (I_C = 5 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	400	750		MHz
Common Emitter Feedback Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{re}		0.25	0.35	pF
Noise Figure (I_C = 4 mA, V_{CE} = 10 V, R_S = 50 Ω, f = 35 MHz)	N_f		2.5		dB

BF224

CASE 29-04, STYLE 21
TO-92 (TO-226AA)



RF TRANSISTOR

NPN SILICON

Refer to BF240 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	45	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current – Continuous	I_C	50	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	°C

THERMAL CHARACTERISTICS

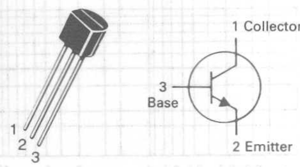
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 1 mAdc, I_B = 0)		$V_{(BR)CEO}$	30			Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)		$V_{(BR)CBO}$	45			Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	4			Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0)	T_A = 25°C	I_{CBO}			100	nAdc
Emitter Cutoff Current (V_{EB} = 3.0 Vdc, I_C = 0)		I_{EBO}			100	nAdc
ON CHARACTERISTICS						
DC Current Gain (I_C = 7 mAdc, V_{CE} = 10 Vdc)		h_{FE}	30			
Base-Emitter On Voltage (I_C = 7 mAdc, V_{CE} = 10 Vdc)		$V_{BE(on)}$		0.77	0.9	mVdc
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{CE(sat)}$			0.15	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current Gain–Bandwidth Product (I_C = 1.5 mAdc, V_{CE} = 10 Vdc, f = 100 MHz) (I_C = 7 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	300	600 850		MHz
Common Emitter Feedback Capacitance (V_{CE} = 10 Vdc, I_E = 0, f = 1 MHz)		C_{re}		0.28		pF
Noise Figure (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, R_S = 50 ohms, f = 100 MHz) f = 200 MHz		N_f		2.5 3.5		dB

BF240
BF241

CASE 29-04, STYLE 21
TO-92 (TO-226AA)



AM/FM TRANSISTORS

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current – Continuous	I_C	25	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (1) (I_C = 1 mAdc, I_B = 0)		$V_{(BR)CEO}$	40			Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)		$V_{(BR)CBO}$	40			Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	4			Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0)		I_{CBO}			100	nAdc
ON CHARACTERISTICS						
DC Current Gain (I_C = 1 mAdc, V_{CE} = 10 Vdc)	BF240 BF241	h_{FE}	65 35		220 125	—
Base-Emitter On Voltage (I_C = 1.0 mAdc, V_{CE} = 10 Vdc)		$V_{BE(on)}$	0.65	0.70	0.74	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current Gain–Bandwidth Product (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	BF240 BF241	f_T		600 470		MHz
Common Emitter Feedback Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{re}		0.28	0.34	pF

(1) Pulse test: Pulse Width ≦ 300 μs, Duty cycle ≦ 2.0%.

2

FIGURE 1 – CURRENT GAIN-BANDWIDTH PRODUCT

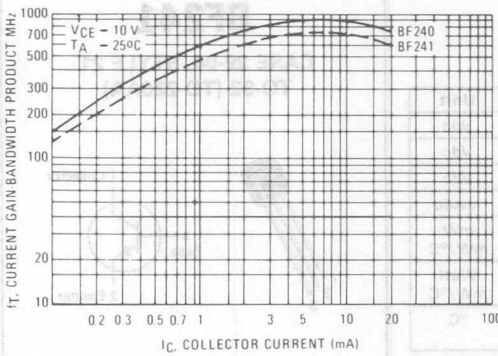


FIGURE 2 – CAPACITANCES

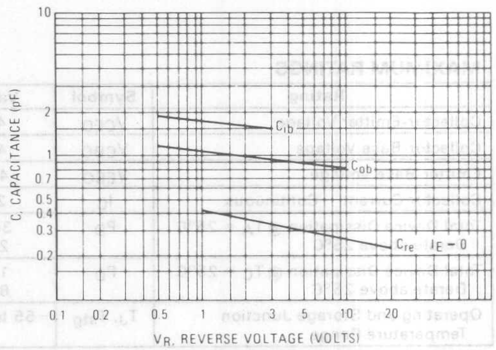


FIGURE 3 – DC CURRENT GAIN

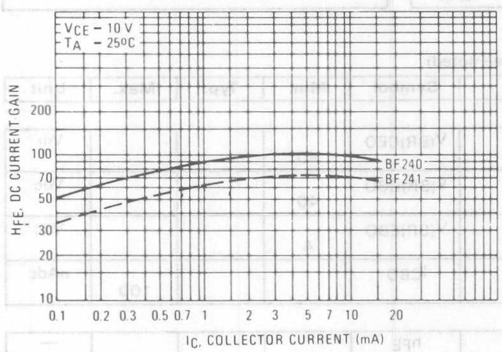


FIGURE 4 – b11e

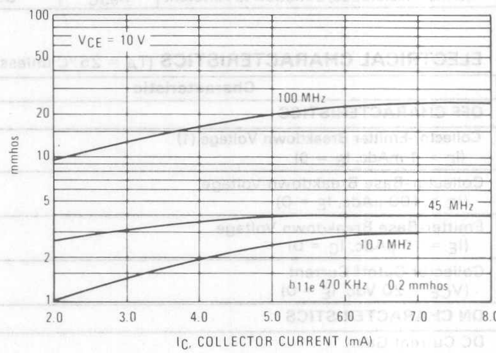


FIGURE 5 – b21e

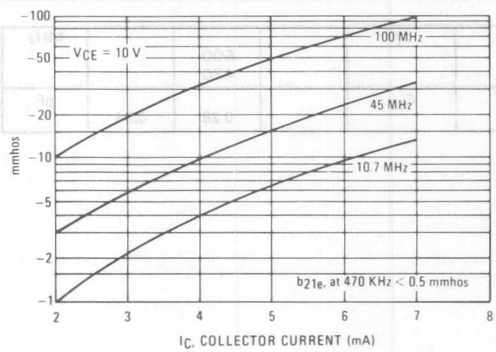


FIGURE 6 – b22e (boe)

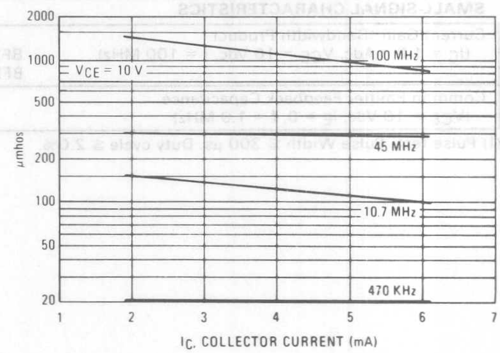


FIGURE 7 — g11e (gie)

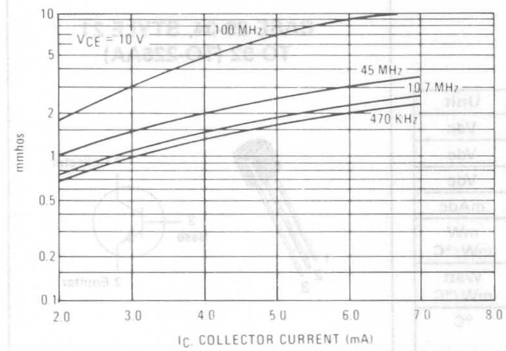


FIGURE 8 — g21e (Yfe)

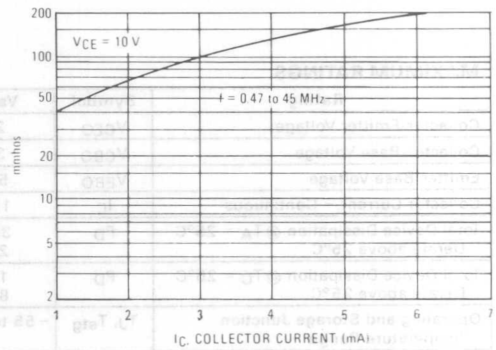
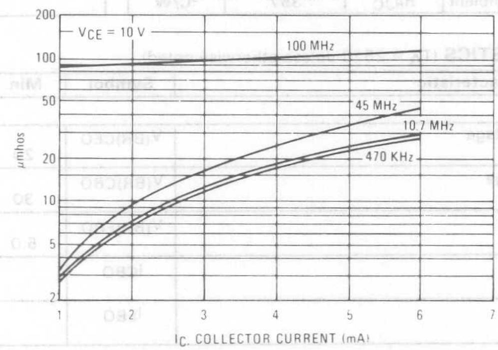


FIGURE 9 — g22e (goe)



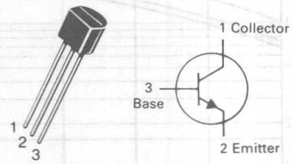
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	20	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous	I_C	100	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	357	°C/W

CASE 29-04, STYLE 21
TO-92 (TO-226AA)



AM/FM TRANSISTORS

NPN SILICON

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)		$V_{(BR)CEO}$	20			Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	30			Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0			Vdc
Collector Cutoff Current (V_{CB} = 10 Vdc, I_E = 0)		I_{CBO}			100	nAdc
Emitter Cutoff Current (V_{EB} = 3.0 Vdc, I_C = 0)		I_{EBO}			100	nAdc
ON CHARACTERISTICS						
DC Current Gain (I_C = 1.0 mA, V_{CE} = 10 Vdc)	BF254 BF254-3 BF254-4	h_{FE}	65 65 100		220 125 220	
Base-Emitter On Voltage (I_C = 1.0 mAdc, V_{CE} = 10 Vdc)	BF254	$V_{BE(on)}$		0.68		Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current Gain–Bandwidth Product (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	BF254	f_T		260		MHz
Common Emitter Feedback Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{re}		0.90		pF
Noise Figure (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1 MHz, R_S = 50 ohms)		N_f		1.7		dB

TYPICAL ADMITTANCE PARAMETERS (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, frequency as stated.)

Symbol	f = 450 kHz BF254	f = 10.7 MHz BF254	Unit
g_{11e}	0.2	0.26	mmhos
b_{11e}	0.05	1.2	mmhos
g_{22e}	3.0	5.3	μmhos
b_{22e}	8.0	190	μmhos
b_{12e}	−5.0	−130	μmhos
g_{12e}	−0.7	−3.0	μmhos
g_{21e}	30	30	mmhos
b_{21e}	−0.003	−0.7	mmhos

FIGURE 1 — DC CURRENT GAIN

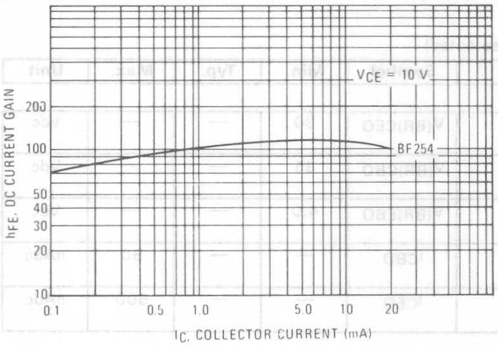


FIGURE 2 — CURRENT GAIN—BANDWITH PRODUCT

FIGURE 3 — "ON" VOLTAGE

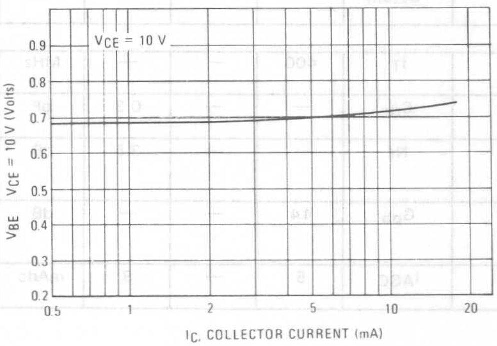
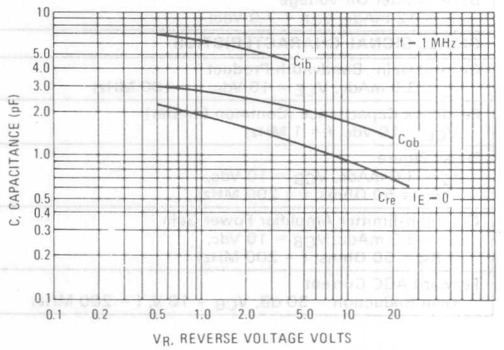


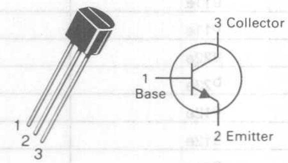
FIGURE 4 — CAPACITANCES



2

BF366

CASE 29-04, STYLE 2
TO-92 (TO-226AA)



VHF TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	35	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current − Continuous	I_C	25	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

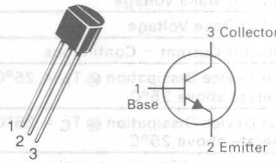
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	35	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 15 Vdc, I_E = 0)	I_{CBO}	—	—	50	nAdc
Collector Cutoff Current (V_{CE} = 12 Vdc, I_B = 0)	I_{CEO}	—	—	500	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 3.0 mAdc, V_{CE} = 10 Vdc) (I_C = 12 mAdc, V_{CE} = 7.0 Vdc)	h_{FE}	 15 5.5	 — —	 — —	—
Base-Emitter On Voltage (I_C = 12 mAdc, V_{CE} = 7.0 Vdc)	$V_{BE(on)}$	—	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current Gain−Bandwidth Product (I_C = 3.0 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	400	—	—	MHz
Feedback Capacitance (Common Emitter) (V_{CE} = 10 Vdc, f = 1 MHz)	C_{rb}	—	—	0.3	pF
Noise Figure (I_C ≈ 3.0 mAdc, V_{CB} ≈ 10 Vdc, R_S = 50 Ohms, f = 200 MHz)	N_f	—	—	3.5	dB
Common-Emitter Amplifier Power Gain (I_C ≈ 3.0 mAdc, V_{CB} ≈ 10 Vdc, R_S = 50 Ohms, f = 200 MHz)	G_{pb}	14	—	—	dB
Forward AGC Current (Gain Reduction = 30 dB, V_{CB} = 10 V, f = 200 MHz)	I_{AGC}	5	—	8	mAdc

BF371
BF373

CASE 29-04, STYLE 2
TO-92 (TO-226AA)



VHF TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	BF 371	BF 373	Unit
Collector-Emitter Voltage	V_{CEO}	30	45	Vdc
Collector-Base Voltage	V_{CBO}	40	45	Vdc
Emitter-Base Voltage	V_{EBO}	4.0		Vdc
Collector Current – Continuous	I_C	100		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	350 2.8		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.0 8.0		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	357	°C/W

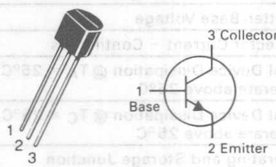
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	BF371 BF373	$V_{(BR)CEO}$	30 45	— —	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	BF371 BF373	$V_{(BR)CBO}$	40 45	— —	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)		I_{CBO}	—	—	50	nAdc
ON CHARACTERISTICS						
DC Current Gain (I_C = 7.0 mAdc, V_{CE} = 10 Vdc) (I_C = 20 mAdc, V_{CE} = 2.0 Vdc)		h_{FE}	40 15	— —	— —	—
Collector-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)		$V_{CE(sat)}$	—	—	0.5	Vdc
Base-Emitter On Voltage (I_C = 7.0 mA, V_{CE} = 10 Vdc)		$V_{BE(on)}$	—	—	0.9	Vdc
DYNAMIC CHARACTERISTICS						
Current-Gain — Bandwidth Product (I_C = 5.0 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	BF371 BF373	f_T	400 500	720 720	— —	MHz
Common-Emitter Feedback Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{re}	—	0.2	0.32	pF

2

BF374
BF375,C,D

CASE 29-04, STYLE 2
TO-92 (TO-226AA)



VHF TRANSISTORS

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current – Continuous	I_C	100	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	350 2.8	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	357	°C/W

Refer to MPSH10 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted)

Characteristic		Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)		$V_{(BR)CEO}$	25			Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	30			Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	3.0			Vdc
Collector Cutoff Current (V_{CB} = 25 Vdc, I_E = 0)		I_{CBO}			100	nAdc
Emitter Cutoff Current (V_{EB} = 2.0 Vdc, I_C = 0)		I_{EBO}			100	nAdc
ON CHARACTERISTICS						
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc)	BF374 BF375 BF375C BF375D	h_{FE}	70 35 70 35		250 120 120 90	
Collector-Emitter Saturation Voltage (I_C = 1.0 mAdc, I_B = 0.1 mAdc) (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{CE(sat)}$			50 70	mVdc mVdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{BE(sat)}$		830		mVdc
Base-Emitter On Voltage (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc		$V_{BE(on)}$		700 770		mVdc mVdc
SMALL-SIGNAL CHARACTERISTICS						
Current Gain–Bandwidth Product (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	400	800		MHz
Common Emitter Feedback Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{re}		0.55	0.6	pF
Collector-Base Time Constant (I_C = 4.0 mAdc, V_{CE} = 10 Vdc, f = 31.8 MHz)		r_bC_c		6		ps
Noise Figure (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 100 MHz, R_S = 50 ohms)		N_f		4		dB
Common-Emitter Amplifier Power Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 200 MHz)		G_{pe}		20		dB

TYPICAL ADMITTANCE PARAMETERS (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, frequency as stated)

Symbol	f = 10.7 MHz	f = 30 MHz	f = 100 MHz	Unit
G_{11e}	0.28	0.4	1.4	mmho
B_{11e}	0.6	1.6	5.0	mmho
G_{22e}	6.5	7	20	µmho
B_{22e}	0.1	0.3	1.0	mmho
G_{21e}	36	34	30	mmho
B_{21e}	− 0.8	− 2.5	− 9	mmho
B_{12e}	− 52	− 150	− 500	µmho

FIGURE 1 — INPUT ADMITTANCE
(Output short circuit)

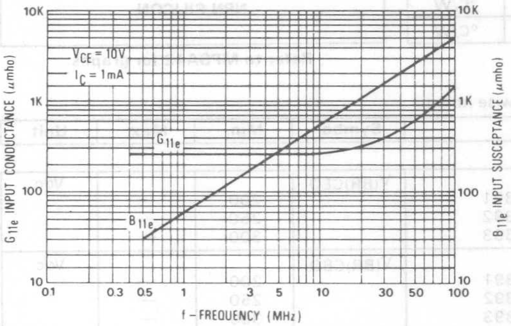


FIGURE 2 — OUTPUT ADMITTANCE
(Input short circuit)

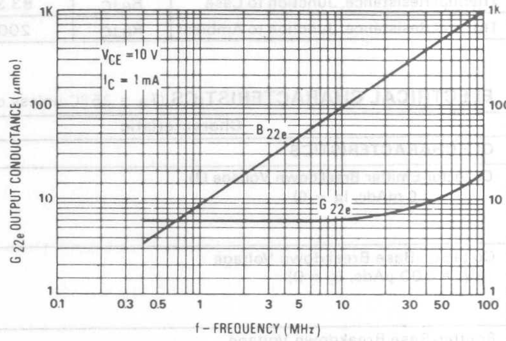


FIGURE 3 — FORWARD TRANSFER ADMITTANCE
(Output short circuit)

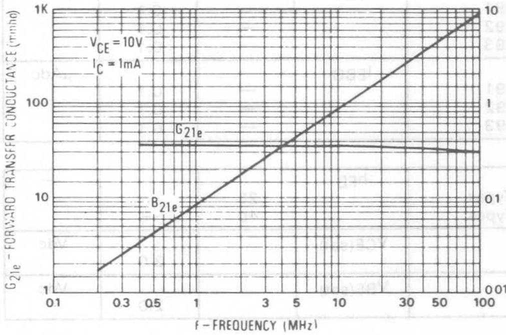
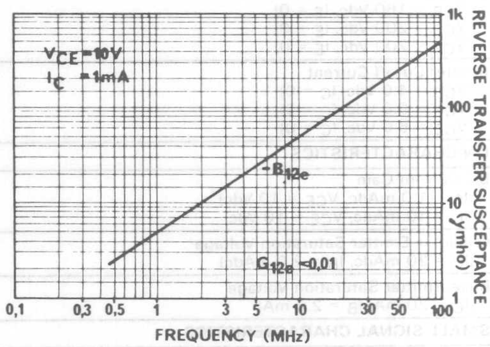
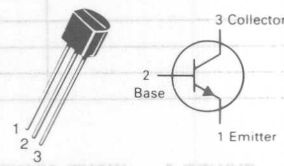


FIGURE 4 — REVERSE TRANSFER ADMITTANCE
(Input short circuit)



BF391
BF392
BF393

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



HIGH VOLTAGE TRANSISTORS

NPN SILICON

Refer to MPSA42 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BF 391	BF 392	BF 393	Unit
Collector-Emitter Voltage	V_{CEO}	200	250	300	Vdc
Collector-Base Voltage	V_{CBO}	200	250	300	Vdc
Emitter-Base Voltage	V_{EBO}	6.0			Vdc
Collector Current − Continuous	I_C	500			mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0			mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12			Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

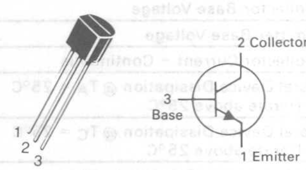
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (1) (I_C = 1.0 mAdc, I_B = 0)	BF391 BF392 BF393	$V_{(BR)CEO}$	200 250 300	— — —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	BF391 BF392 BF393	$V_{(BR)CBO}$	200 250 300	— — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	BF391 BF392 BF393	$V_{(BR)EBO}$	6.0 6.0 6.0	— — —	Vdc
Collector Cutoff Current (V_{CB} = 160 Vdc, I_E = 0) (V_{CB} = 200 Vdc, I_E = 0) (V_{CB} = 200 Vdc, I_E = 0)	BF391 BF392 BF393	I_{CBO}	— — —	0.1 0.1 0.1	μAdc
Emitter Cutoff Current (V_{CB} = 4.0 Vdc, I_C = 0) (V_{CB} = 6.0 Vdc, I_C = 0) (V_{CB} = 6.0 Vdc, I_C = 0)	BF391 BF392 BF393	I_{EBO}	— — —	0.1 0.1 0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc)	All Types All Types	h_{FE}	25 40	— —	—
Collector-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)		$V_{CE(sat)}$		2.0	Vdc
Base-Emitter Saturation Voltage (I_C = 20 mA, I_B = 2.0 mA)		$V_{BE(sat)}$		2.0	Vdc
SMALL SIGNAL CHARACTERISTICS					
Current-Gain − Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 20 MHz)		f_T	50	—	MHz
Common Emitter Feedback Capacitance (V_{CB} = 60 Vdc, I_E = 0, f = 1.0 MHz)		C_{re}		2.0	pF

(1) Pulse Test: Pulse Width ≦ 300 μs, Duty Cycle ≦ 2.0%.

BF420
BF422

CASE 29-04, STYLE 14
TO-92 (TO-226AA)



HIGH VOLTAGE TRANSISTORS

NPN SILICON

Refer to MPSA42 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BF 420	BF 422	Unit
Collector-Emitter Voltage	V_{CEO}	300	250	Vdc
Collector-Base Voltage	V_{CBO}	300	250	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	800 6.4		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	2.75 22		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	45	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	156	°C/W

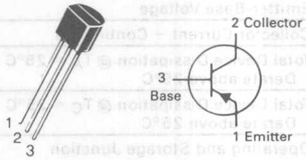
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (1) (I_C = 1 mAdc, I_B = 0)	BF420 BF422	$V_{(BR)CEO}$	300 250	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	BF420 BF422	$V_{(BR)CBO}$	300 250	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	BF420 BF422	$V_{(BR)EBO}$	5.0 5.0	— —	Vdc
Collector Cutoff Current (V_{CB} = 200 Vdc, I_E = 0)	BF420 BF422	I_{CBO}	—	0.01	μAdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)	BF420 BF422	I_{EBO}	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 25 mAdc, V_{CE} = 20 Vdc)	BF420 BF422	h_{FE}	50 50	— —	—
Collector-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)		$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter Saturation Voltage (I_C = 20 mA, I_B = 2.0 mA)		$V_{BE(sat)}$	—	2.0	Vdc
SMALL SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 50 MHz)		f_T	60	—	MHz
Common Emitter Feedback Capacitance (V_{CB} = 30 Vdc, I_E = 0, f = 1.0 MHz)		C_{re}	—	1.6	pF

(1) Pulse Test: Pulse Width ≦ 300 μs, Duty Cycle ≦ 2.0%.

BF423

CASE 29-04, STYLE 14
TO-92 (TO-226AA)



HIGH VOLTAGE TRANSISTORS

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	BF 421	BF 423	Unit
Collector-Emitter Voltage	V_{CEO}	300	250	Vdc
Collector-Base Voltage	V_{CBO}	300	250	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current – Continuous	I_C	500		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	800 6.4		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.75 22		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	45	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	156	°C/W

Refer to MPSA92 for graphs.

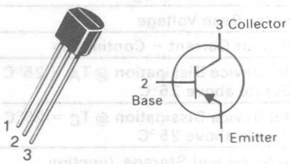
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted)

Characteristic		Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (1) ($I_C = 1$ mAdc, $I_B = 0$)	BF421 BF423	$V_{(BR)CEO}$	300 250	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	BF421 BF423	$V_{(BR)CBO}$	300 250	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	BF421 BF423	$V_{(BR)EBO}$	5.0 5.0	— —	Vdc
Collector Cutoff Current ($V_{CB} = 200$ Vdc, $I_E = 0$)	BF421 BF423	I_{CBO}	—	0.01	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$)	BF421 BF423	I_{EBO}	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 25$ mA, $V_{CE} = 20$ Vdc)	BF421 BF423	h_{FE}	50 50	— —	
Collector-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)		$V_{CE(sat)}$		0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 20$ mA, $I_B = 2.0$ mA)		$V_{BE(sat)}$		2.0	Vdc
SMALL SIGNAL CHARACTERISTICS					
Current-Gain – Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 50 MHz)		f_T	60		MHz
Common Emitter Feedback Capacitance ($V_{CB} = 30$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{re}		2.8	pF

(1) Pulse Test: Pulse Width ≦ 300 μs, Duty Cycle ≦ 2.0%.

BF493

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



HIGH VOLTAGE TRANSISTORS

PNP SILICON

Refer to MPSA92 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BF 491	BF 492	BF 493	Unit
Collector-Emitter Voltage	V_{CEO}	200	250	300	Vdc
Collector-Base Voltage	V_{CBO}	200	250	300	Vdc
Emitter-Base Voltage	V_{EBO}	6.0			Vdc
Collector Current − Continuous	I_C	500			mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0			mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12			Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

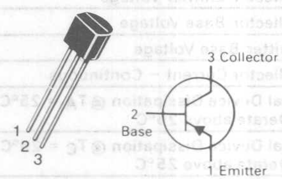
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (1) (I_C = 1 mAdc, I_B = 0)	BF491 BF492 BF493	$V_{(BR)CEO}$	200 250 300	— — —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	BF491 BF492 BF493	$V_{(BR)CBO}$	200 250 300	— — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	BF491 BF492 BF493	$V_{(BR)EBO}$	6.0 6.0 6.0	— — —	Vdc
Collector Cutoff Current (V_{CB} = 160 Vdc, I_E = 0) (V_{CB} = 200 Vdc, I_E = 0) (V_{CB} = 200 Vdc, I_E = 0)	BF491 BF492 BF493	I_{CBO}	— — —	0.1 0.1 0.1	μAdc
Emitter Cutoff Current (V_{CB} = 4.0 Vdc, I_C = 0) (V_{CB} = 6.0 Vdc, I_C = 0) (V_{CB} = 6.0 Vdc, I_C = 0)	BF491 BF492 BF493	I_{EBO}	— — —	0.1 0.1 0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc)	All Types All Types	h_{FE}	25 40	— —	—
Collector-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)		$V_{CE(sat)}$	—	2.0	Vdc
Base-Emitter Saturation Voltage (I_C = 20 mA, I_B = 2.0 mA)		$V_{BE(sat)}$	—	2.0	Vdc
SMALL SIGNAL CHARACTERISTICS					
Current-Gain − Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 20 MHz)		f_T	50	—	MHz
Common Emitter Feedback Capacitance (V_{CB} = 100 Vdc, I_E = 0, f = 1.0 MHz)		C_{re}		1.6	pF

(1) Pulse Test: Pulse Width ≦ 300 μs, Duty Cycle ≦ 2.0%.

BF493S

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



HIGH VOLTAGE TRANSISTOR

PNP SILICON

Refer to MPSA93 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	350	Vdc
Collector-Base Voltage	V_{CBO}	350	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current − Continuous	I_C	500	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

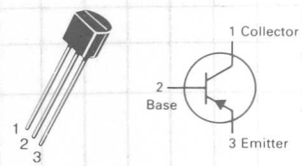
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	350	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	350	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current (V_{CE} = 250 Vdc)	I_{CES}	—	10	nAdc
Emitter Cutoff Current (V_{BE} = 6.0 Vdc, I_C = 0)	I_{EBO}	—	0.1	μAdc
Collector Cutoff Current (V_{CB} = 250 Vdc, I_E = 0, T_A = 25°C) (V_{CB} = 250 Vdc, I_E = 0, T_A = 100°C)	I_{CBO}	 — —	 0.005 1.0	μAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc)	h_{FE}	 25 40	 — —	—
Collector-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)	$V_{CE(sat)}$	—	2.0	Vdc
Base-Emitter On Voltage (I_C = 20 mA, I_B = 2.0 mA)	$V_{BE(sat)}$	—	2.0	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 20 MHz)	f_T	50		MHz
Common-Emitter Feedback Capacitance (V_{CB} = 100 Vdc, I_E = 0, f = 1.0 MHz)	C_{re}	—	1.6	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

BF506

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



VHF TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	35	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current − Continuous	I_C	50	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

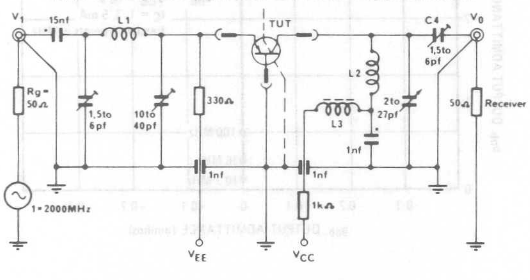
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	357	°C/W

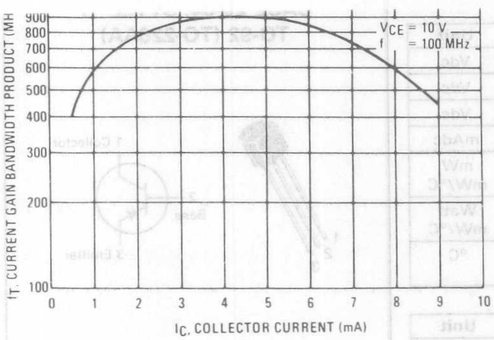
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 5.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	35	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	4	—	—	Vdc
Collector Cutoff Current (V_{CB} = 20 V, I_E = 0)	I_{CBO}	—	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 3 mAdc, V_{CE} = 10 Vdc)	h_{FE}	25	—	—	
SMALL SIGNAL CHARACTERISTICS					
Current-Gain Bandwidth Product (I_C = 2 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	450	—	650	MHz
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{CBO}	—	0.6	0.9	pF
Feedback Capacitance (Grounded Base) (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{rb}	—	0.15	0.25	pF
Noise Figure (I_C = 2 mA, R_S = 50 Ω, f = 100 MHz, V_{CC} = 10 V)	N_F	—	2.5	3	dB
Power Gain (I_C = 3 mA, R_L = 1 KΩ, f = 200 MHz, V_{CC} = 10.8 V)	G_{pb}	14	22	—	dB

200 MHz POWER GAIN NOISE FIGURE TEST CIRCUIT



*Leadless ceramic disc capacitor
L1 = 3 turns 0.0 mm enamel, 4 mm dia.
L2 = 2 turns 1 mm enamel, 6.5 mm dia.



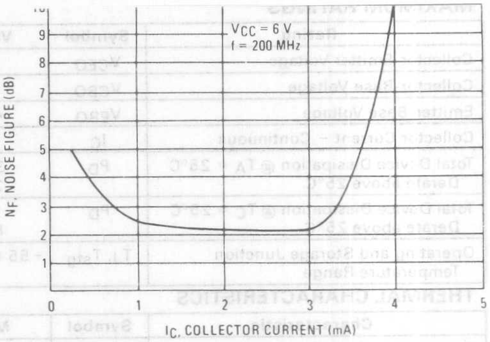


FIGURE 3 – FORWARD TRANSFER ADMITTANCE

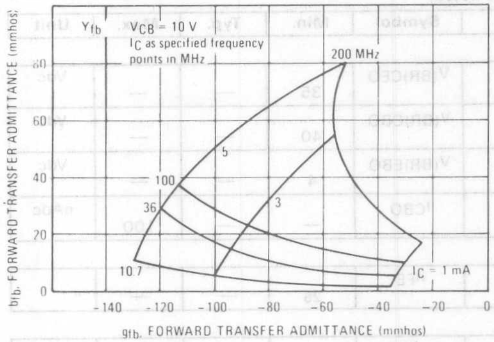


FIGURE 4 – INPUT ADMITTANCE

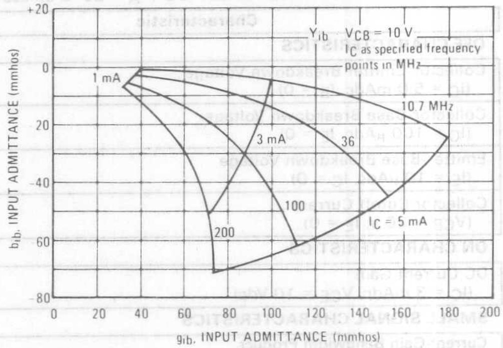
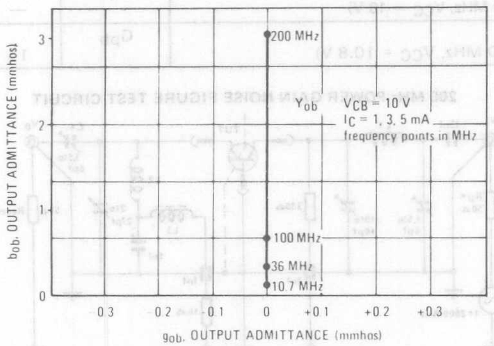


FIGURE 5 – OUTPUT ADMITTANCE



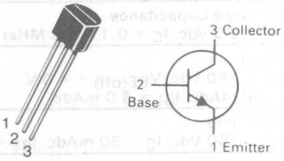
MAXIMUM RATINGS

Rating	Symbol	BF 844	BF 845	Unit
Collector-Emitter Voltage	V_{CEO}	400	350	Vdc
Collector-Base Voltage	V_{CBO}	450	400	Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	300		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



VOLTAGE TRANSISTORS

NPN SILICON

Refer to MPSA44 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	 BF844 BF845	$V_{(BR)CEO}$	 400 350	 — —	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 100$ µAdc, $V_{BE} = 0$)	 BF844 BF845	$V_{(BR)CES}$	 450 400	 — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ µAdc, $I_E = 0$)	 BF844 BF845	$V_{(BR)CBO}$	 450 400	 — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ µAdc, $I_C = 0$)	Both Types	$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 400$ Vdc, $I_E = 0$) ($V_{CB} = 320$ Vdc, $I_E = 0$)	 BF844 BF845	I_{CBO}	 — —	 0.1 0.1	µAdc
Collector Cutoff Current ($V_{CE} = 400$ Vdc, $V_{BE} = 0$) ($V_{CE} = 320$ Vdc, $V_{BE} = 0$)	 BF844 BF845	I_{CES}	 — —	 500 500	nAdc
Emitter Cutoff Current ($V_{BE} = 4.0$ Vdc, $I_C = 0$)	Both Types	I_{EBO}	—	0.1	µAdc
ON CHARACTERISTICS					
DC Current Gain (1) ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 10$ Vdc)	 Both Types Both Types Both Types Both Types	h_{FE}	 40 50 45 20	 — 200 — —	—
Collector-Emitter Saturation Voltage (1) ($I_C = 1.0$ mAdc, $I_B = 0.1$ mAdc) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)	 Both Types Both Types Both Types	$V_{CE(sat)}$	 — — —	 0.4 0.5 0.75	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)		$V_{BE(sat)}$	—	0.75	Vdc

(1) Pulse Test: Pulse Width ≦ 300 µS — Duty Cycle ≦ 2.0%.

2

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
DYNAMIC CHARACTERISTICS					
High Frequency Current Gain (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 10 MHz)	Both Types	$\|h_{fe}\|$	2.0	—	
Collector-Base Capacitance (V_{CB} = 20 Vdc, I_E = 0, f = 1.0 MHz)	Both Types	C_{ob}	—	6.0	pF
Emitter-Base Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	Both Types	C_{ib}	—	110	pF
Turn-On Time (V_{CC} = 150 Vdc, $V_{BE(off)}$ = 4.0 V, I_C = 30 mAdc, I_{B1} = 3.0 mAdc)	Both Types	t_{on}	—	0.6	µs
Turn-Off Time (V_{CC} = 150 Vdc, I_C = 30 mAdc, I_{B1} = I_{B2} = 3.0 mAdc)	Both Types	t_{off}	—	10	µs

FIGURE 1 — DC CURRENT GAIN

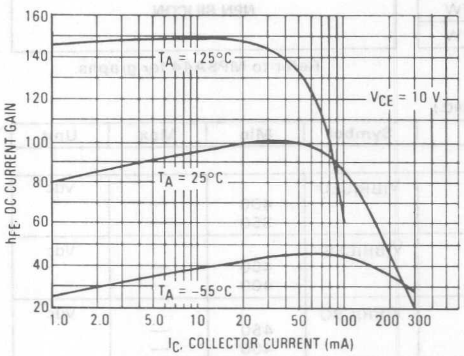
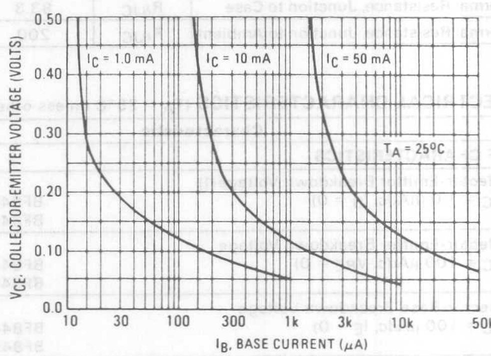
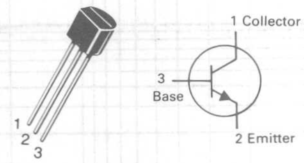


FIGURE 2 — COLLECTOR SATURATION REGION



BF959

CASE 29-04, STYLE 21
TO-92 (TO-226AA)



VHF TRANSISTOR

NPN SILICON

2

MAXIMUM RATINGS

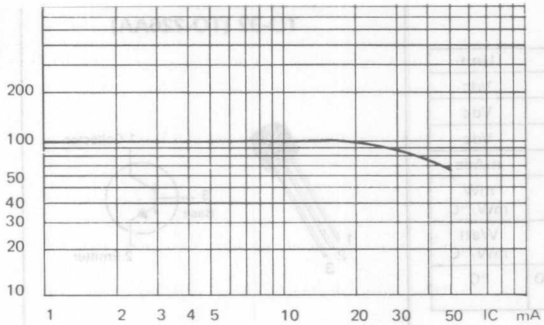
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	20	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current – Continuous	I_C	100	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	20	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	30	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	3.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0)	I_{CBO}	—	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 5 mAdc, V_{CE} = 10 Vdc) (I_C = 20 mAdc, V_{CE} = 10 Vdc)	h_{FE}	 35 40	 — —	 — —	
Collector-Emitter Saturation Voltage (I_C = 30 mAdc, I_B = 2.0 mAdc)	$V_{CE(sat)}$	—	—	1.0	Vdc
Base-Emitter Saturation Voltage (I_C = 30 mAdc, I_B = 2.0 mAdc)	$V_{BE(sat)}$	—	—	1	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain – Bandwidth Product (I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 100 MHz) (I_C = 30 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_t	 700 600	 — —	 — —	MHz
Common Emitter Feedback Capacitance (V_{CB} = 10 Vdc, P_f = 0, f = 10 MHz)	C_{re}	—	0.65'	—	pF
Noise Figure (I_C = 4 mA, V_{CE} = 10 V, R_S = 50 Ω, f = 200 MHz)	N_f	—	3	—	dB



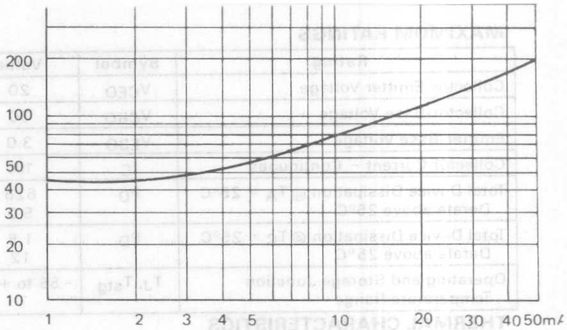


FIGURE 3 – CURRENT-GAIN – BANDWIDTH-PRODUCT

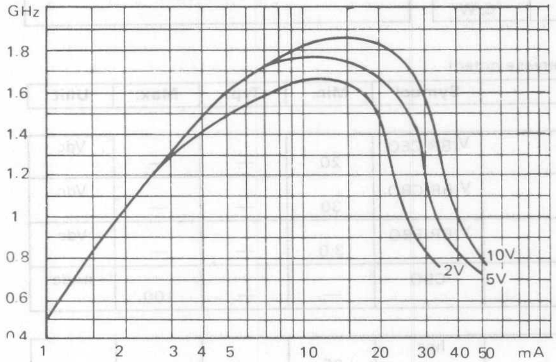


FIGURE 4 – CAPACITANCES

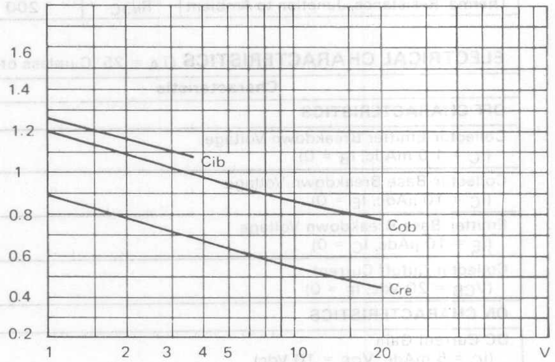


FIGURE 5 – INPUT IMPEDANCE AT 30 MHz

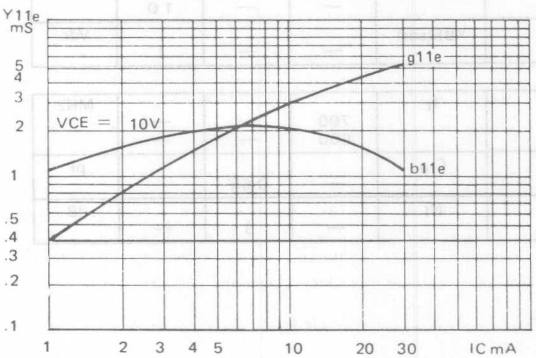
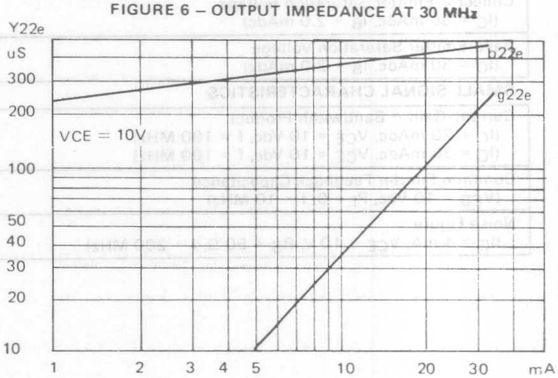
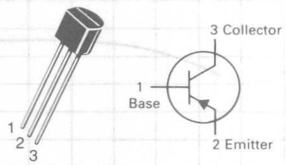


FIGURE 6 – OUTPUT IMPEDANCE AT 30 MHz



CASE 29-04, STYLE 2
TO-92 (TO-226AA)



HIGH FREQUENCY TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	MPS536	Unit
Collector-Emitter Voltage	V_{CEO}	10	Vdc
Collector-Base Voltage	V_{CBO}	15	Vdc
Emitter-Base Voltage	V_{EBO}	4.5	Vdc
Collector Current — Continuous	I_C	30	mA
Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Storage Temperature	T_{stg}	−65 to +150	°C

*Free air

ELECTRICAL CHARACTERISTICS (T_C = 25°C *For both package types unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 2.0 mA, I_B = 0)	$V_{(BR)CEO}$	10	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μA, I_E = 0)	$V_{(BR)CBO}$	15	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μA, I_C = 0)	$V_{(BR)EBO}$	4.5	—	—	Vdc
Collector Cutoff Current (V_{CB} = 10 Vdc, I_E = 0)	I_{CBO}	—	—	10	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 20 mA, V_{CE} = 5.0 V)	h_{FE}	20	—	200	—
DYNAMIC CHARACTERISTICS					
Current Gain-Bandwidth Product (I_C = 20 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 GHz)	f_T	—	4.5	—	GHz
Collector-Base Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	—	0.8	1.2	pF
FUNCTIONAL TESTS					
Gain @ Noise Figure (I_C = 10 mAdc, V_{CE} = 5.0 Vdc) f = 500 MHz f = 1.0 GHz	G_{NF}	 — —	 14 8.0	 — —	dB
Noise Figure (I_C = 10 mAdc, V_{CE} = 5.0 Vdc) f = 500 MHz f = 1.0 GHz	NF	 — —	 4.5 6.0	 — —	dB

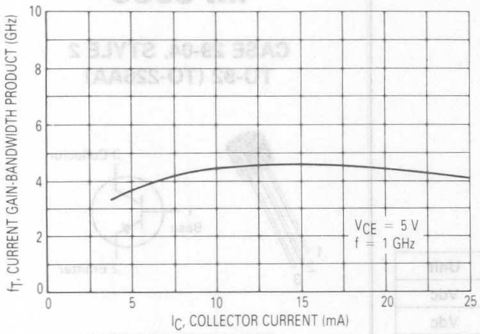


Figure 1. Current Gain-Bandwidth Product versus Collector Current

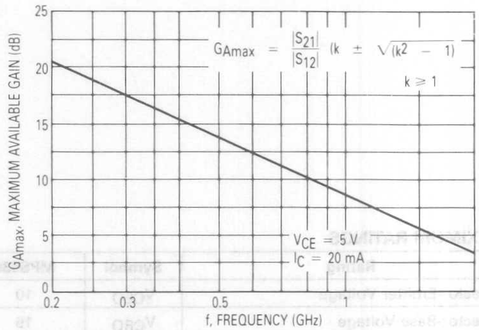


Figure 2. Maximum Available Gain (G_{Amax}) versus Frequency

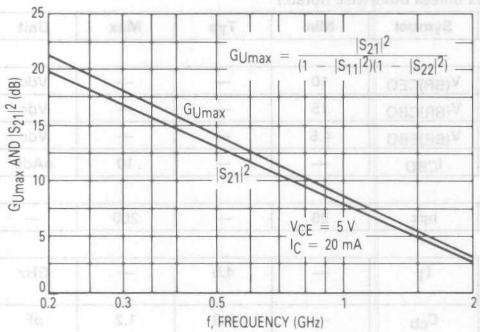


Figure 3. Maximum Unilateral Gain (G_{Umax}) and Insertion Gain ($|S_{21}|^2$) versus Frequency

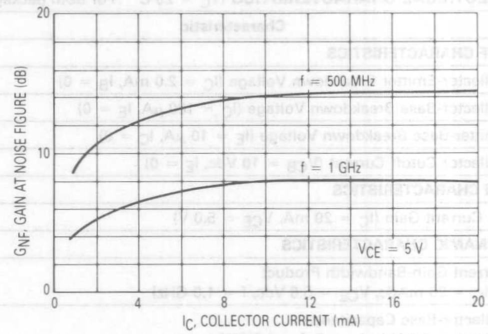


Figure 4. Gain at Noise Figure versus Collector Current

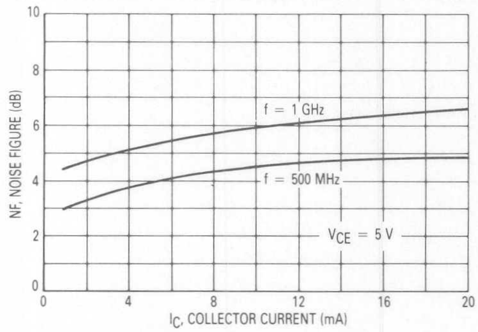


Figure 5. Noise Figure versus Collector Current

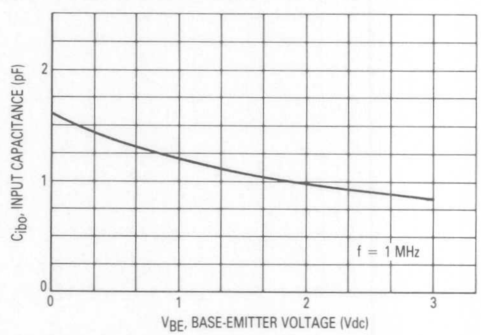


Figure 6. Input Capacitance versus Emitter-Base Voltage

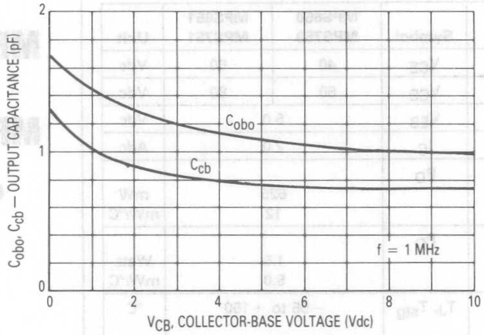
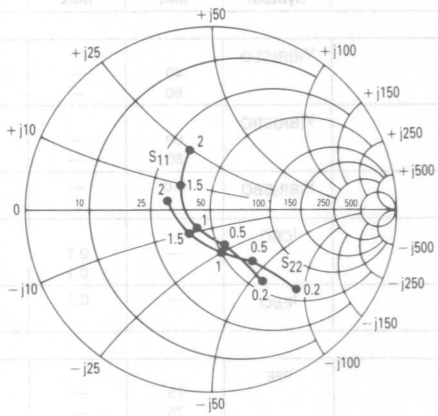
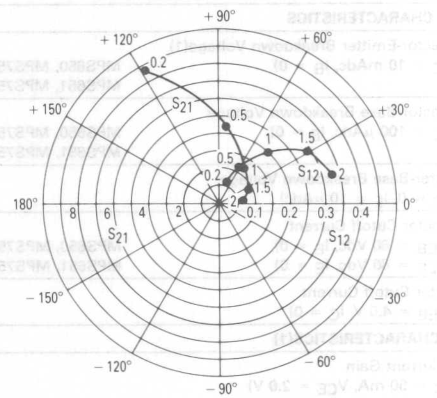


Figure 7. Output Capacitance versus Collector-Base Voltage

INPUT/OUTPUT REFLECTION COEFFICIENT versus FREQUENCY V_{CE} = 10 V, I_C = 10 mA



FORWARD/REVERSE TRANSMISSION COEFFICIENTS versus FREQUENCY V_{CE} = 10 V, I_C = 10 mA



COMMON EMITTER S-PARAMETERS

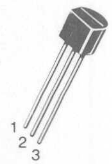
V_{CE} (Volts)	I_C (mA)	f (MHz)	S_{11}		S_{21}		S_{12}		S_{22}	
			$\|S_{11}\|$	$\angle\phi$	$\|S_{21}\|$	$\angle\phi$	$\|S_{12}\|$	$\angle\phi$	$\|S_{22}\|$	$\angle\phi$
10	5	200	0.60	−43	6.60	125	0.07	68	0.71	−35
		500	0.30	−60	3.64	87	0.14	57	0.47	−43
		1000	0.17	−103	2.11	56	0.22	43	0.32	−69
		1500	0.15	156	1.70	28	0.30	28	0.22	+112
		2000	0.28	110	1.29	2	0.33	13	0.25	−174
	10	200	0.48	−52	8.78	118	0.06	69	0.62	−42
		500	0.21	−66	4.31	84	0.12	60	0.37	−46
		1000	0.12	−122	2.40	54	0.20	47	0.24	−73
		1500	0.18	138	1.90	29	0.29	31	0.16	−126
		2000	0.32	104	1.41	4	0.33	16	0.23	170
	20	200	0.38	−59	10.21	112	0.06	70	0.54	−46
		500	0.14	−76	4.72	81	0.12	63	0.30	−47
		1000	0.11	−144	2.58	53	0.20	49	0.19	−74
		1500	0.22	132	1.99	28	0.29	34	0.12	−139
		2000	0.35	103	1.46	4	0.33	19	0.22	161

2

Collector-Emitter Voltage	V_{CE}	40	60	Vdc
Collector-Base Voltage	V_{CB}	60	80	Vdc
Emitter-Base Voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous	I_C	2.0		Adc
Total Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 12		mW mW/°C
Total Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.5 5.0		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

PNP
MPS750, MPS751

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	 MPS650, MPS750 MPS651, MPS751	$V_{(BR)CEO}$	 40 60	 — —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	 MPS650, MPS750 MPS651, MPS751	$V_{(BR)CBO}$	 60 80	 — —	Vdc
Emitter-Base Breakdown Voltage (I_C = 0, I_E = 10 μAdc)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 60 Vdc, I_E = 0) (V_{CB} = 80 Vdc, I_E = 0)	 MPS650, MPS750 MPS651, MPS751	I_{CBO}	 — —	 0.1 0.1	μAdc
Emitter Cutoff Current (V_{EB} = 4.0 V, I_C = 0)		I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 50 mA, V_{CE} = 2.0 V) (I_C = 500 mA, V_{CE} = 2.0 V) (I_C = 1.0 A, V_{CE} = 2.0 V) (I_C = 2.0 A, V_{CE} = 2.0 V)		h_{FE}	 75 75 75 40	 — — — —	—
Collector-Emitter Saturation Voltage (I_C = 2.0 A, I_B = 200 mA) (I_C = 1.0 A, I_B = 100 mA)		$V_{CE(sat)}$	 — —	 0.5 0.3	Vdc
Base-Emitter On Voltage (I_C = 1.0 A, V_{CE} = 2.0 V)		$V_{BE(on)}$	—	1.0	Vdc
Base-Emitter Saturation Voltage (I_C = 1.0 A, I_B = 100 mA)		$V_{BE(sat)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 50 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)		f_T	75	—	MHz

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 2.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

FIGURE 1 — MPS650, MPS651
TYPICAL DC CURRENT GAIN
NPN

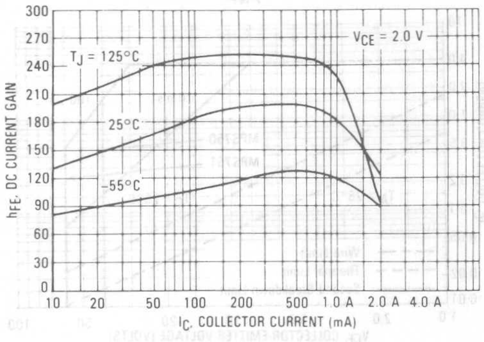


FIGURE 2 — MPS750, MPS751
TYPICAL DC CURRENT GAIN
PNP

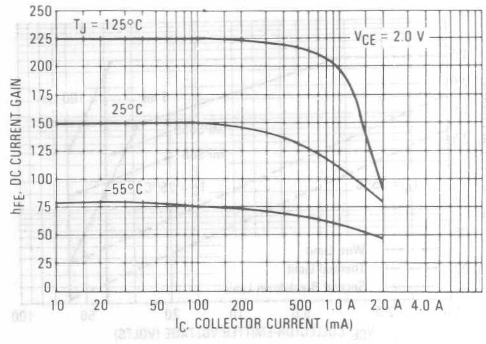


FIGURE 3 — MPS650, MPS651
ON VOLTAGES
NPN

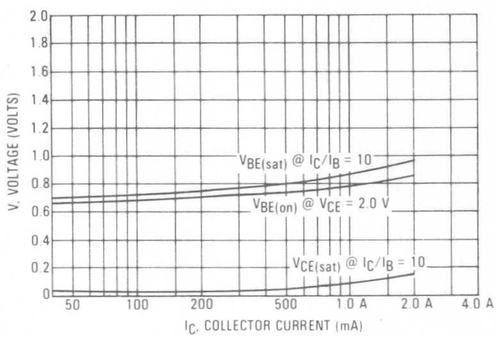


FIGURE 4 — MPS750, MPS751
ON VOLTAGES
PNP

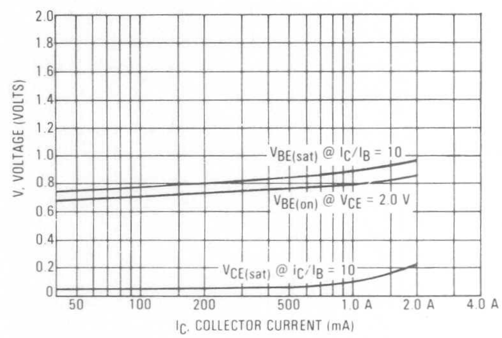


FIGURE 5 — MPS650, MPS651
COLLECTOR SATURATION REGION
NPN

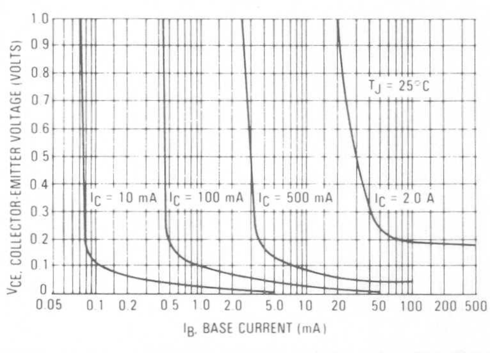


FIGURE 6 — MPS750, MPS751
COLLECTOR SATURATION REGION
PNP

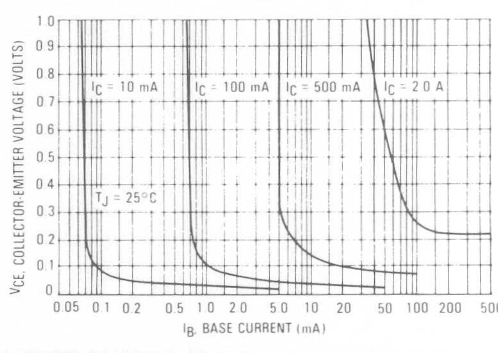


FIGURE 7 — MPS650, MPS651 SOA, SAFE OPERATING AREA

NPN

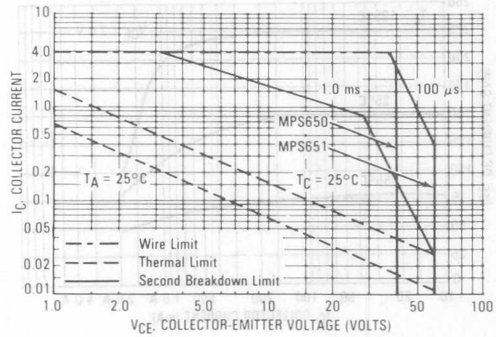
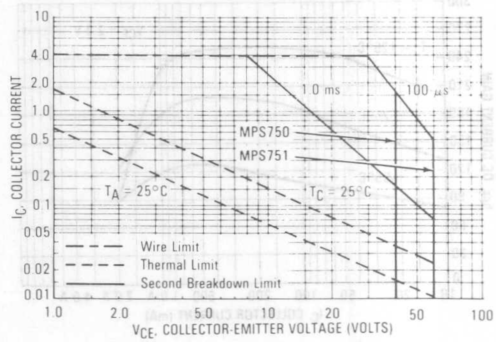


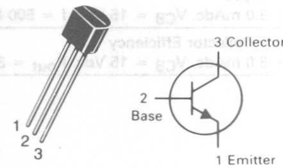
FIGURE 8 — MPS750, MPS751 SOA, SAFE OPERATING AREA

PNP



MPS918
MPS3563

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	MPS918	MPS3563	Unit
Collector-Emitter Voltage	V_{CEO}	15	12	Vdc
Collector-Base Voltage	V_{CBO}	30	30	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	2.0	Vdc
Collector Current — Continuous	I_C	50		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 3.0 mAdc, I_B = 0)	 MPS918 MPS3563	$V_{(BR)CEO}$	 15 12	 — —	Vdc
Collector-Base Breakdown Voltage (I_C = 1.0 μAdc, I_E = 0) (I_C = 100 μAdc, I_E = 0)	 MPS918 MPS3563	$V_{(BR)CBO}$	 30 30	 — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	 MPS918 MPS3563	$V_{(BR)EBO}$	 3.0 2.0	 — —	Vdc
Collector Cutoff Current (V_{CB} = 15 Vdc, I_E = 0)	 MPS918 MPS3563	I_{CBO}	 — —	 10 50	nAdc
ON CHARACTERISTICS					
DC Current Gain(2) (I_C = 3.0 mAdc, V_{CE} = 1.0 Vdc) (I_C = 8.0 mAdc, V_{CE} = 10 Vdc)	 MPS918 MPS3563	h_{FE}	 20 20	 — 200	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	 MPS918	$V_{CE(sat)}$	—	0.4	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	 MPS918	$V_{BE(sat)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 4.0 mAdc, V_{CE} = 10 Vdc, f = 100 MHz) (I_C = 8.0 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	 MPS918 MPS3563	f_T	 600 600	 — 1500	MHz
Output Capacitance (V_{CB} = 0 Vdc, I_E = 0, f = 140 kHz) (V_{CB} = 10 Vdc, I_E = 0, f = 140 kHz) (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	 MPS918 MPS918 MPS3563	C_{obo}	 — — —	 3.0 1.7 1.7	pF
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 140 kHz)	 MPS918	C_{ibo}	—	2.0	pF
Small-Signal Current Gain (I_C = 8.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	 MPS3563	h_{fe}	20	250	—
Noise Figure (I_C = 1.0 mAdc, V_{CE} = 6.0 Vdc, R_S = 400 ohms, f = 60 MHz)	 MPS918	NF	—	6.0	dB

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.
(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 1.0%.

2

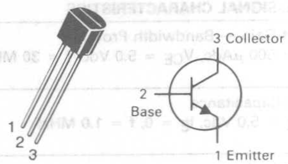
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
FUNCTIONAL TEST					
Common-Emitter Amplifier Power Gain		G_{pe}			dB
(I_C = 6.0 mAdc, V_{CB} = 12 Vdc, f = 200 MHz)	MPS918		15		
(I_C = 8.0 mAdc, V_{CE} = 10 Vdc, f = 200 MHz)	MPS3563		14	—	
(G_{fd} + G_{re} < −20 dB)					
Power Output (I_C = 8.0 mAdc, V_{CB} = 15 Vdc, f = 500 MHz)	MPS918	P_{out}	30	—	mW
Oscillator Collector Efficiency (I_C = 8.0 mAdc, V_{CB} = 15 Vdc, P_{out} = 30 mW, f = 500 MHz)	MPS918	η	25	—	%

Rating	Symbol	MPS929	MPS930A	Unit
Collector-Emitter Voltage	V_{CEO}	45		Vdc
Collector-Base Voltage	V_{CBO}	45	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	6.0	Vdc
Collector Current — Continuous	I_C	100		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

MPS930A

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MPS3903 for additional graphs.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)		$V_{(BR)CEO}$	45	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	MPS929 MPS930A	$V_{(BR)CBO}$	45 60	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	MPS929 MPS930A	$V_{(BR)EBO}$	5.0 6.0	— —	Vdc
Collector Cutoff Current (V_{CE} = 5.0 Vdc, I_B = 0)		I_{CEO}	—	2.0	nAdc
Collector Cutoff Current (V_{CB} = 45 Vdc, I_E = 0)	MPS929 MPS930A	I_{CBO}	— —	10 2.0	nAdc
Collector Cutoff Current (V_{CE} = 45 Vdc, V_{BE} = 0)	MPS929 MPS930A	I_{CES}	— —	10 2.0	nAdc
(V_{CE} = 45 Vdc, V_{BE} = 0, T_A = 125°C)	MPS929 MPS930A		— —	10 2.0	μAdc
Emitter Cutoff Current (V_{EB} = 5.0 Vdc, I_C = 0)	MPS929 MPS930A	I_{EBO}	— —	10 2.0	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 1.0 μAdc, V_{CE} = 5.0 Vdc)	MPS930A	h_{FE}	60	—	—
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc)	MPS929 MPS930A		40 100	120 300	
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc, T_A = −55°C)	MPS929 MPS930A		10 30	— —	
(I_C = 500 μAdc, V_{CE} = 5.0 Vdc)	MPS929 MPS930A		60 150	— —	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	MPS929 MPS930A		— —	350 600	

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Collector-Emitter Saturation Voltage(1) (I_C = 10 mAdc, I_B = 0.5 mAdc)	MPS929	$V_{CE(sat)}$	—	1.0	Vdc
	MPS930A		—	0.5	
Base-Emitter Saturation Voltage(1) (I_C = 10 mAdc, I_B = 0.5 mAdc)	MPS929	$V_{BE(sat)}$	0.6	1.0	Vdc
	MPS930A		0.7	0.9	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 500 μAdc, V_{CE} = 5.0 Vdc, f = 30 MHz)	MPS929	f_T	30	—	MHz
	MPS930A		45	—	
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	MPS929	C_{obo}	—	8.0	pF
	MPS930A		—	6.0	
Input Impedance (I_E = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)		h_{ib}	25	32	Ohms
Voltage Feedback Ratio (I_E = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)		h_{rb}	—	600	X 10^{-6}
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	MPS929	h_{fe}	60	350	—
	MPS930A		150	600	
Output Admittance (I_E = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)		h_{ob}	—	1.0	μmho
Noise Figure (I_C = 10 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 kohms, f = 10 Hz to 15.7 kHz)	MPS929	NF	—	4.0	dB
	MPS930A		—	3.0	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

TYPICAL CHARACTERISTICS

FIGURE 1 – DC CURRENT GAIN

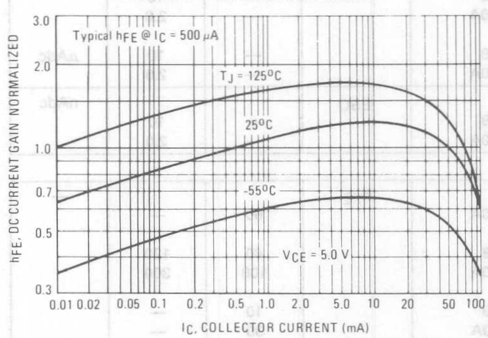


FIGURE 2 – "ON" VOLTAGES

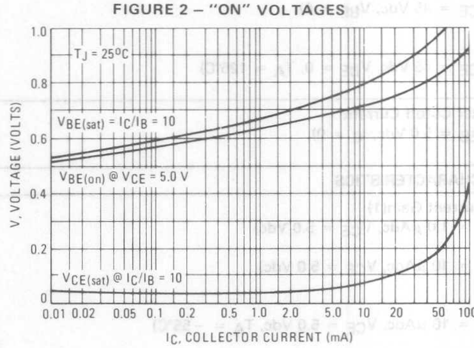


FIGURE 3 – COLLECTOR SATURATION REGION

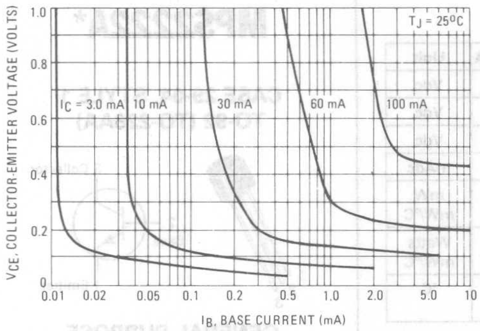


FIGURE 4 – TEMPERATURE COEFFICIENTS

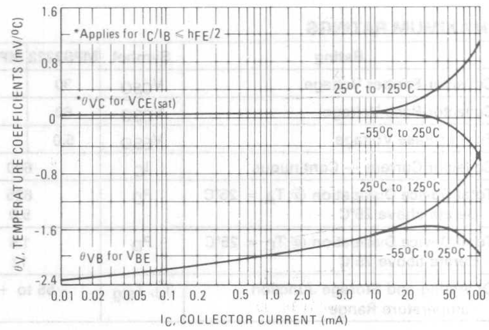


FIGURE 5 – CURRENT-GAIN – BANDWIDTH PRODUCT

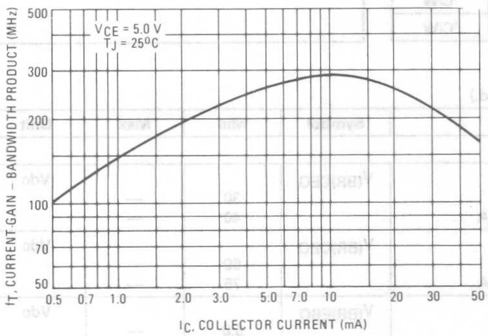
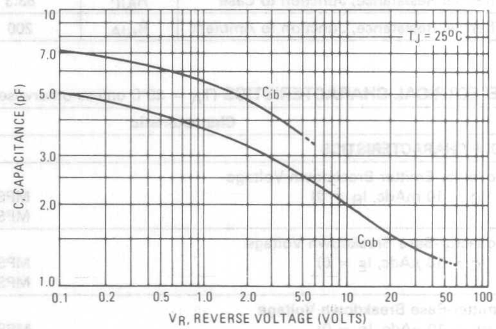


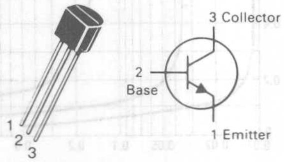
FIGURE 6 – CAPACITANCES



2

MPS2222A*

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	MPS2222	MPS2222A	Unit
Collector-Emitter Voltage	V_{CEO}	30	40	Vdc
Collector-Base Voltage	V_{CBO}	60	75	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	6.0	Vdc
Collector Current — Continuous	I_C	600		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	 MPS2222 MPS2222A	$V_{(BR)CEO}$	 30 40	 — —	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	 MPS2222 MPS2222A	$V_{(BR)CBO}$	 60 75	 — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	 MPS2222 MPS2222A	$V_{(BR)EBO}$	 5.0 6.0	 — —	Vdc
Collector Cutoff Current (V_{CE} = 60 Vdc, $V_{EB(off)}$ = 3.0 Vdc)	 MPS2222A	I_{CEX}	—	10	nAdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0) (V_{CB} = 60 Vdc, I_E = 0) (V_{CB} = 50 Vdc, I_E = 0, T_A = 125°C) (V_{CB} = 50 Vdc, I_E = 0, T_A = 125°C)	 MPS2222 MPS2222A MPS2222 MPS2222A	I_{CBO}	 — — — —	 0.01 0.01 10 10	μAdc
Emitter Cutoff Current (V_{EB} = 3.0 Vdc, I_C = 0)	 MPS2222A	I_{EBO}	—	10	nAdc
Base Cutoff Current (V_{CE} = 60 Vdc, $V_{EB(off)}$ = 3.0 Vdc)	 MPS2222A	I_{BL}	—	20	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 0.1 mAdc, V_{CE} = 10 Vdc) (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc, T_A = −55°C) (I_C = 150 mAdc, V_{CE} = 10 Vdc)(1) (I_C = 150 mAdc, V_{CE} = 1.0 Vdc)(1) (I_C = 500 mAdc, V_{CE} = 10 Vdc)(1)	 MPS2222A only MPS2222 MPS2222A	h_{FE}	 35 50 75 35 100 50 30 40	 — — — — 300 — — —	—
Collector-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)	 MPS2222 MPS2222A MPS2222 MPS2222A	$V_{CE(sat)}$	 — — — —	 0.4 0.3 1.6 1.0	Vdc

*Also available as a PN2222,A.

Characteristic		Symbol	Min	Max	Unit
Base-Emitter Saturation Voltage(1)		$V_{BE(sat)}$			Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)	MPS2222		—	1.3	
	MPS2222A		0.6	1.2	
(I_C = 500 mAdc, I_B = 50 mAdc)	MPS2222		—	2.6	
	MPS2222A		—	2.0	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2)		f_T			MHz
(I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	MPS2222		250	—	
	MPS2222A		300	—	
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	8.0	pF
Input Capacitance		C_{ibo}			pF
(V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	MPS2222		—	30	
	MPS2222A		—	25	
Input Impedance		h_{ie}			kΩ
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MPS2222A		2.0	8.0	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MPS2222A		0.25	1.25	
Voltage Feedback Ratio		h_{re}			$X\ 10^{-4}$
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MPS2222A		—	8.0	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MPS2222A		—	4.0	
Small-Signal Current Gain		h_{fe}			—
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MPS2222A		50	300	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MPS2222A		75	375	
Output Admittance		h_{oe}			μmhos
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MPS2222A		5.0	35	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MPS2222A		25	200	
Collector Base Time Constant (I_E = 20 mAdc, V_{CB} = 20 Vdc, f = 31.8 MHz)	MPS2222A	$rb'C_c$	—	150	ps
Noise Figure (I_C = 100 μAdc, V_{CE} = 10 Vdc, R_S = 1.0 kΩ, f = 1.0 kHz)	MPS2222A	NF	—	4.0	dB
SWITCHING CHARACTERISTICS MPS2222A only					
Delay Time	(V_{CC} = 30 Vdc, $V_{BE(off)}$ = 0.5 Vdc,	t_d	—	10	ns
Rise Time	I_C = 150 mAdc, I_{B1} = 15 mAdc) (Figure 1)	t_r	—	25	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc,	t_s	—	225	ns
Fall Time	I_{B1} = I_{B2} = 15 mAdc) (Figure 2)	t_f	—	60	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

FIGURE 1 – TURN-ON TIME

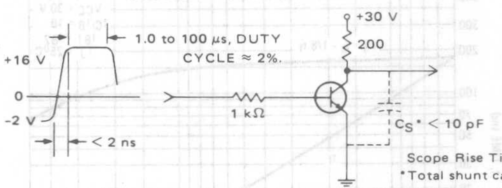
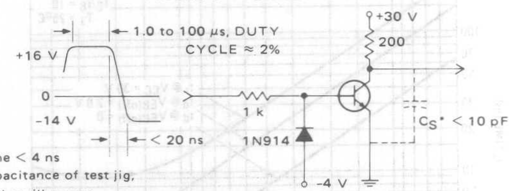


FIGURE 2 – TURN-OFF TIME



Scope Rise Time < 4 ns
*Total shunt capacitance of test jig, connectors, and oscilloscope.

FIGURE 3 – DC CURRENT GAIN

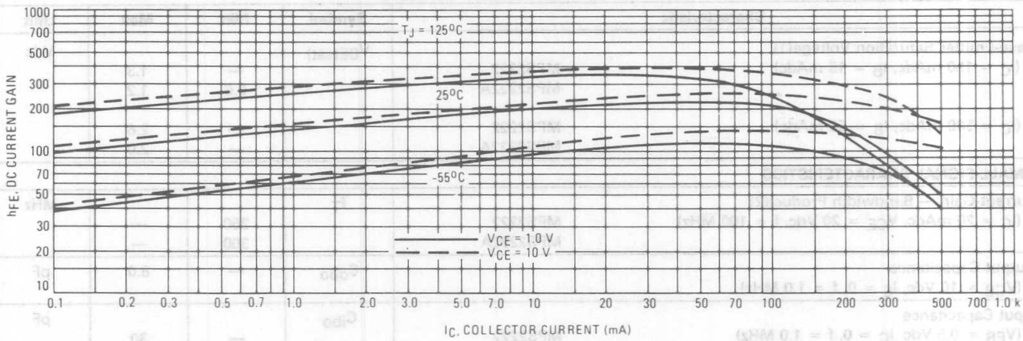


FIGURE 4 – COLLECTOR SATURATION REGION

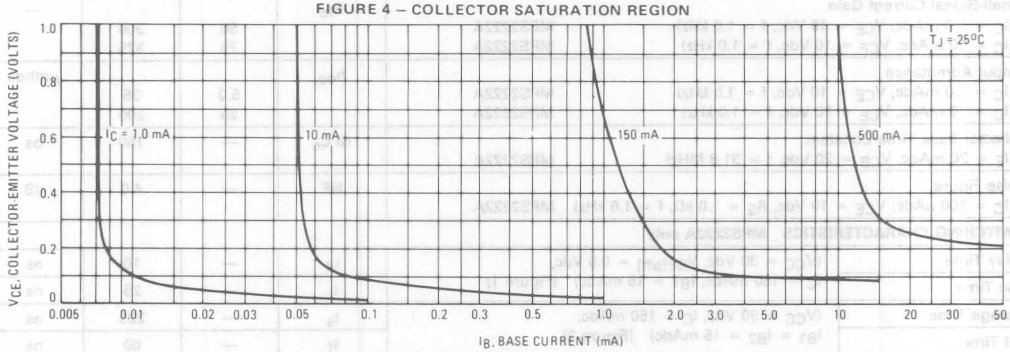


FIGURE 5 – TURN-ON TIME

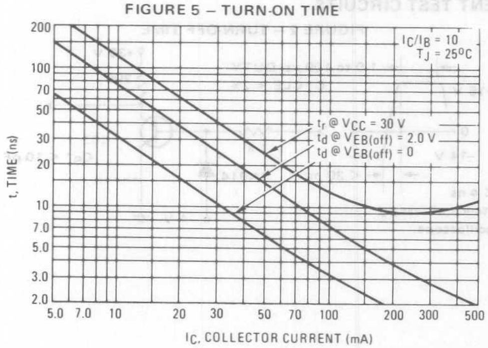


FIGURE 6 – TURN-OFF TIME

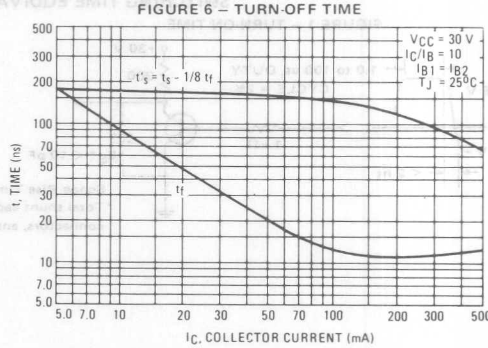


FIGURE 7 – FREQUENCY EFFECTS

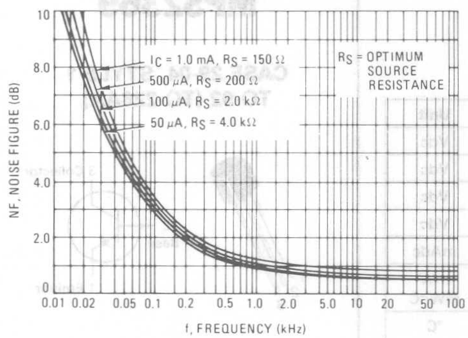


FIGURE 8 – SOURCE RESISTANCE EFFECTS

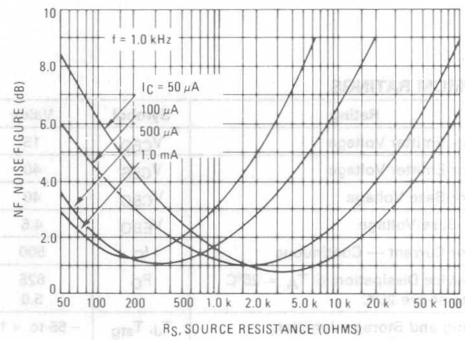


FIGURE 9 – CAPACITANCES

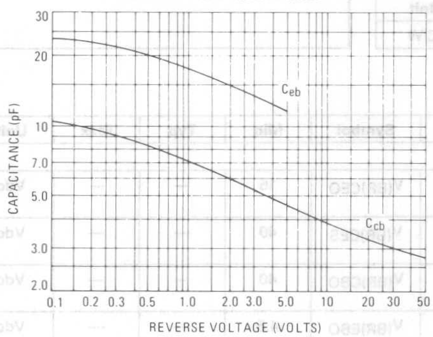


FIGURE 10 – CURRENT-GAIN BANDWIDTH PRODUCT

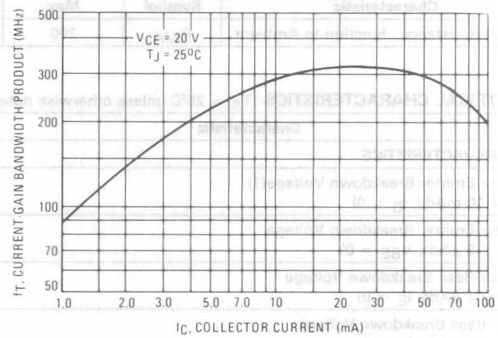


FIGURE 11 – "ON" VOLTAGES

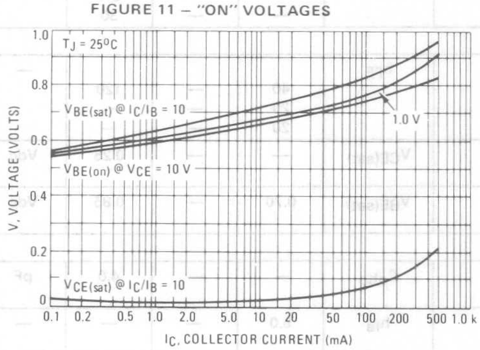
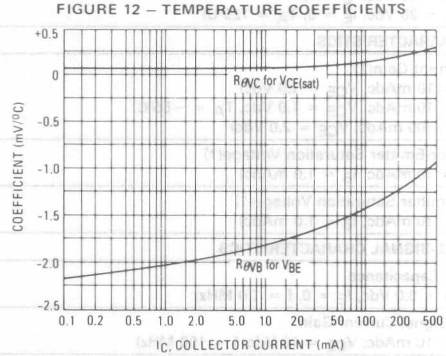
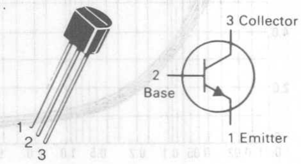


FIGURE 12 – TEMPERATURE COEFFICIENTS



MPS2369

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



SWITCHING TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Emitter Voltage	V_{CES}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4.5	Vdc
Collector Current — Continuous	I_C	500	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	15	—	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 10\ \mu$Adc, $V_{BE} = 0$)	$V_{(BR)CES}$	40	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	4.5	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$) ($V_{CB} = 20$ Vdc, $I_E = 0$, $T_A = 125°C$)	I_{CBO}	 — —	 — —	 0.4 30	μAdc
ON CHARACTERISTICS					
DC Current Gain(1) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc, $T_A = -55°C$) ($I_C = 100$ mAdc, $V_{CE} = 2.0$ Vdc)	h_{FE}	 40 20 20	 — — —	 120 — —	—
Collector-Emitter Saturation Voltage(1) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	—	0.25	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	0.70	—	0.85	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{obo}	—	—	4.0	pF
Small-Signal Current Gain ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	h_{fe}	5.0		—	—
SWITCHING CHARACTERISTICS					
Storage Time ($I_{B1} = I_{B2} = I_C = 10$ mAdc) (Figure 3)	t_s	—	5.0	13	ns
Turn-On Time ($V_{CC} = 3.0$ Vdc, $I_C = 10$ mAdc, $I_{B1} = 3.0$ mAdc) (Figure 1)	t_{on}	—	8.0	12	ns
Turn-Off Time ($V_{CC} = 3.0$ Vdc, $I_C = 10$ mAdc, $I_{B1} = 3.0$ mAdc, $I_{B2} = 1.5$ mAdc) (Figure 2)	t_{off}	—	10	18	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — t_{on} CIRCUIT

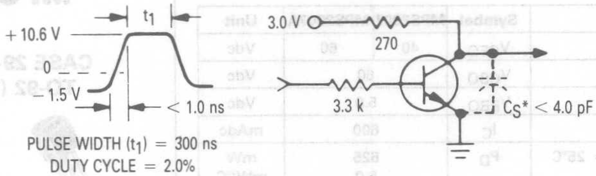


FIGURE 2 — t_{off} CIRCUIT

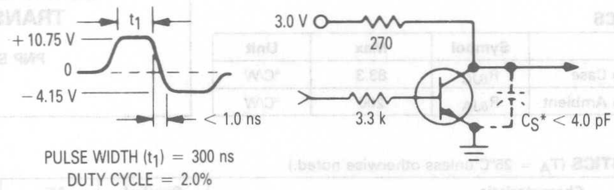
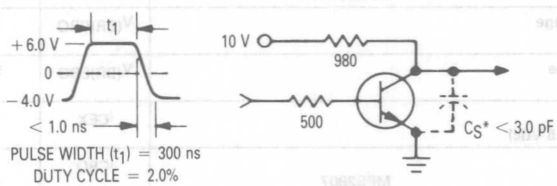


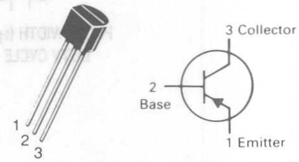
FIGURE 3 — STORAGE TEST CIRCUIT



*TOTAL SHUNT CAPACITANCE OF TEST JIG AND CONNECTORS.

MPS2907
MPS2907A

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	MPS2907	MPS2907A	Unit
Collector-Emitter Voltage	V_{CEO}	40	60	Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	600		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	MPS2907 MPS2907A	$V_{(BR)CEO}$	40 60	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)		$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 30$ Vdc, $V_{BE(off)} = 0.5$ Vdc)		I_{CEX}	—	50	nAdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$)	MPS2907 MPS2907A	I_{CBO}	— —	0.020 0.010	μAdc
($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = 125°C$)	MPS2907 MPS2907A		— —	20 10	
Base Current ($V_{CE} = 30$ Vdc, $V_{BE(off)} = 0.5$ Vdc)		I_B	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 10$ Vdc)	MPS2907 MPS2907A	h_{FE}	35 75	— —	—
($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc)	MPS2907 MPS2907A		50 100	— —	
($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc)	MPS2907 MPS2907A		75 100	— —	
($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)(1)	MPS2907, MPS2907A		100	300	
($I_C = 500$ mAdc, $V_{CE} = 10$ Vdc)(1)	MPS2907 MPS2907A		30 50	— —	
Collector-Emitter Saturation Voltage(1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)		$V_{CE(sat)}$	— —	0.4 1.6	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)		$V_{BE(sat)}$	— —	1.3 2.6	Vdc

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(1),(2) (I_C = 50 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)		f_T	200	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	8.0	pF
Input Capacitance (V_{BE} = 2.0 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	30	pF
SWITCHING CHARACTERISTICS					
Turn-On Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc) (Figures 1 and 5)	t_{on}	—	45	ns
Delay Time		t_d	—	10	ns
Rise Time		t_r	—	40	ns
Turn-Off Time	(V_{CC} = 6.0 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc) (Figure 2)	t_{off}	—	100	ns
Storage Time		t_s	—	80	ns
Fall Time		t_f	—	30	ns

(1) Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

FIGURE 1 – DELAY AND RISE TIME TEST CIRCUIT

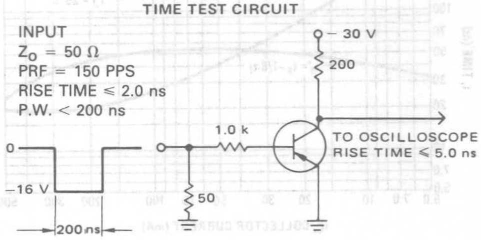
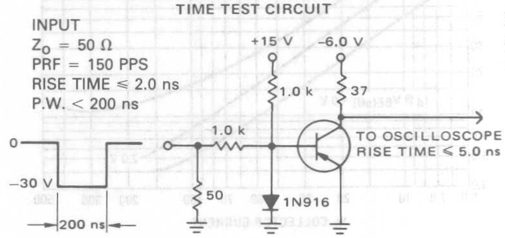


FIGURE 2 – STORAGE AND FALL TIME TEST CIRCUIT



TYPICAL CHARACTERISTICS

FIGURE 3 – DC CURRENT GAIN

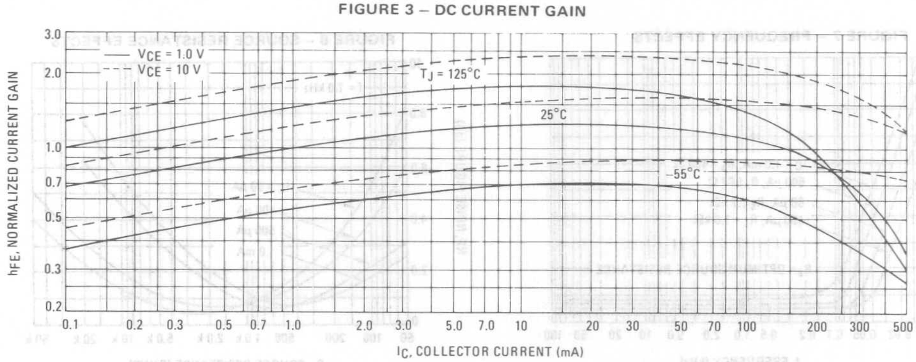


FIGURE 4 – COLLECTOR SATURATION REGION

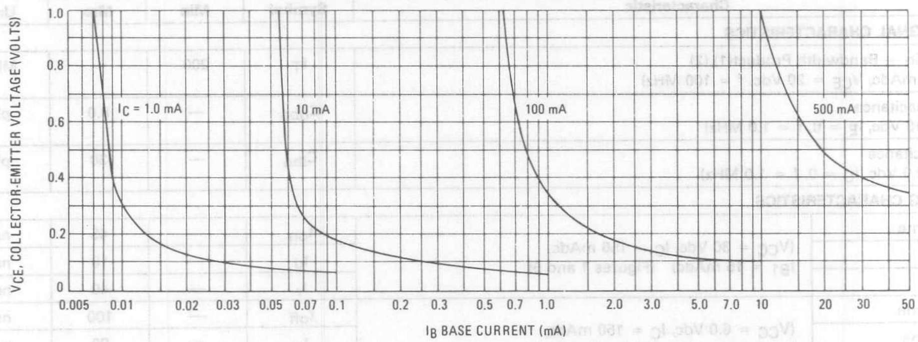


FIGURE 5 – TURN-ON TIME

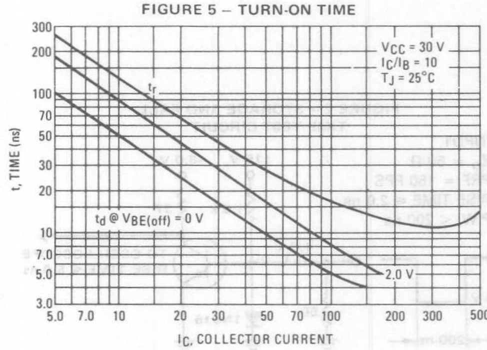
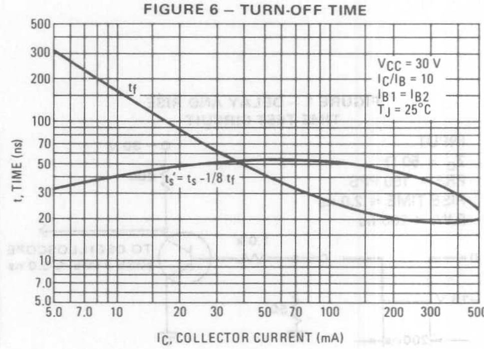


FIGURE 6 – TURN-OFF TIME



TYPICAL SMALL-SIGNAL CHARACTERISTICS
NOISE FIGURE
V_{CE} = 10 Vdc, T_A = 25°C

FIGURE 7 – FREQUENCY EFFECTS

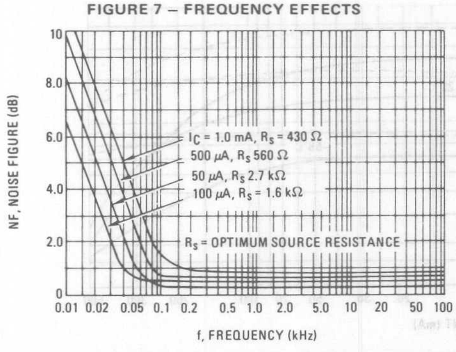


FIGURE 8 – SOURCE RESISTANCE EFFECTS

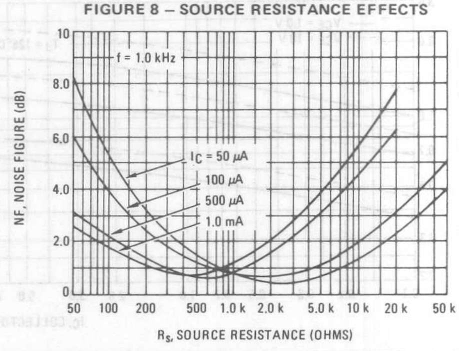


FIGURE 9 — CAPACITANCES

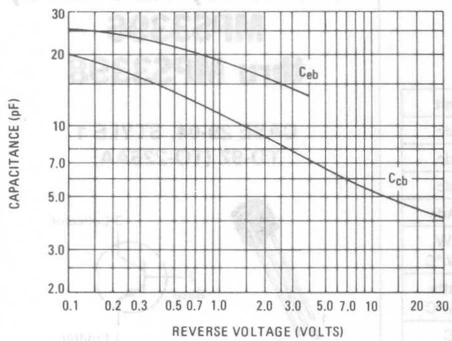


FIGURE 10 — CURRENT-GAIN — BANDWIDTH PRODUCT

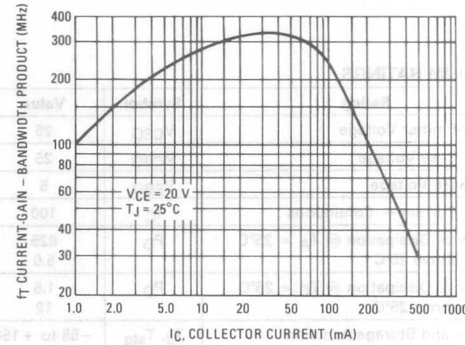


FIGURE 11 — "ON" VOLTAGE

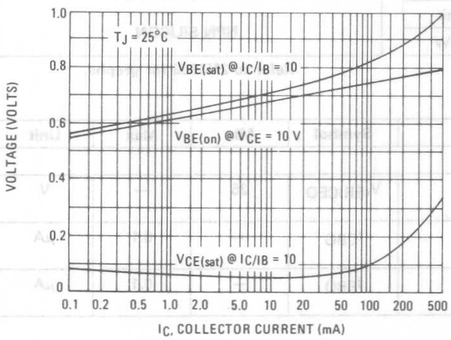
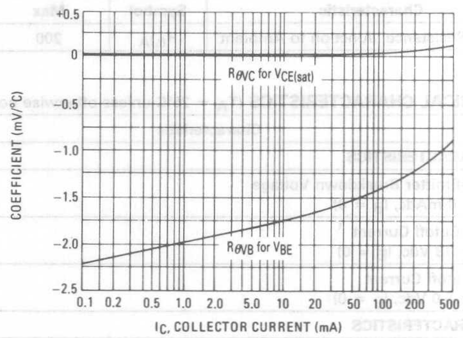
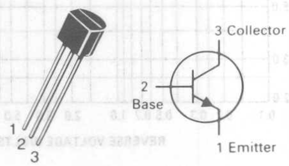


FIGURE 12 — TEMPERATURE COEFFICIENTS



MPS3390, MPS3391, MPS3396 thru MPS3398

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N3903 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	25	Vdc
Emitter-Base Voltage	V_{EBO}	5	Vdc
Collector Current — Continuous	I_C	100	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

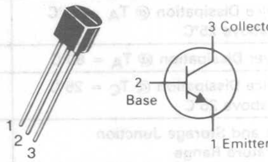
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	25	—	V
Collector Cutoff Current ($V_{CB} = 18$ Vdc, $I_E = 0$)		I_{CBO}	—	0.1	μA
Emitter Cutoff Current ($V_{EB} = 5.0$ Vdc, $I_C = 0$)		I_{EBO}	—	0.1	μA
ON CHARACTERISTICS					
DC Current Gain ($V_{CE} = 4.5$ Vdc, $I_C = 2.0$ mAdc)	MPS3390 MPS3391 MPS3396 MPS3397 MPS3398	h_{FE}	400 250 90 55 55	800 500 500 500 800	—
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance ($V_{CB} = 10$ V, $I_E = 0$, f = 1.0 MHz)		C_{obo}	—	10	pF
Small-Signal Current Gain ($V_{CE} = 4.5$ V, $I_C = 2.0$ mA, f = 1.0 kHz)	MPS3390 MPS3391 MPS3396 MPS3397 MPS3398	h_{fe}	400 250 90 55 55	1250 800 800 800 1250	—

2

MPS3403

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	25	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	500	mA
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

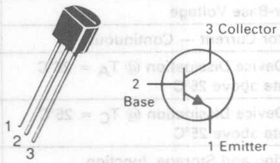
Refer to MPS8098 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 1.0 mA)	$V_{(BR)CEO}$	25	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μA)	$V_{(BR)CBO}$	25	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μA)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 18 V) (V_{CB} = 18 V, T_A = 100°C)	I_{CBO}	 — —	 100 15	 nA μA
Emitter Cutoff Current (V_{BE} = 5.0 V)	I_{EBO}	—	100	nA
ON CHARACTERISTICS				
DC Current Gain (I_C = 2.0 mA, V_{CE} = 4.5 V)	h_{FE}	180	540	—
Collector-Emitter Saturation Voltage (I_C = 50 mA, I_B = 3.0 mA)	$V_{CE(sat)}$	—	0.3	Vdc
Base-Emitter Saturation Voltage (I_C = 50 mA, I_B = 3.0 mA)	$V_{BE(sat)}$	0.6	1.3	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Small-Signal Current Gain (I_C = 2.0 mA, V_{CE} = 4.5 V, f = 1.0 kHz) (I_C = 2.0 mA, V_{CE} = 4.5 V, f = 1.0 kHz)	h_{fe}	 75 180	 —	—

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Power Dissipation @ $T_A = 60°C$	P_D	450	mW
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N4400 for graphs.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

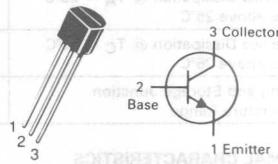
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) (I_C = 30 mA)	$V_{(BR)CEO(sus)}$	30	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μA)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μA)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 20 V) (V_{CB} = 20 V, T_A = 75°C)	I_{CBO}	 — —	 50 5.0	 nA μA
Emitter Cutoff Current (V_{BE} = 5.0 V)	I_{EBO}	—	10	μA
ON CHARACTERISTICS				
DC Current Gain (I_C = 10 mA, V_{CE} = 10 V) (I_C = 2.0 mA, V_{CE} = 10 V)	h_{FE}	 150 80	 600 —	—
Collector-Emitter Saturation Voltage (I_C = 100 mA, I_B = 10 mA)	$V_{CE(sat)}$	—	1.0	Vdc
Base-Emitter On Voltage(1) (I_C = 100 mA, V_{CE} = 1.0 V)	$V_{BE(on)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance (V_{CB} = 10 V, f = 1.0 MHz)	C_{obo}	—	25	pF
Small-Signal Current Gain (I_C = 30 mA, V_{CE} = 10 V, f = 20 MHz)	h_{fe}	2.0	35	—

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MPS3567
MPS3568
MPS3569

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N4400 for graphs for MPS3567, 3569.*

MAXIMUM RATINGS

Rating	Symbol	MPS3567 MPS3569	MPS3568	Unit
Collector-Emitter Voltage	V_{CEO}	40	60	Vdc
Collector-Base Voltage	V_{CBO}	80		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	600		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

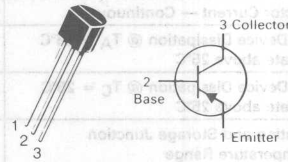
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage(1) ($I_C = 30$ mAdc, $I_B = 0$)	 MPS3567, MPS3569 MPS3568	$V_{CEO(sus)}$	 40 60	 — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)		$V_{(BR)CBO}$	80	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 40$ Vdc, $I_E = 0$) ($V_{CB} = 40$ Vdc, $I_E = 0$, $T_A = 75°C$)		I_{CBO}	 — —	 50 5.0	 nAdc μAdc
Emitter Cutoff Current ($V_{EB} = 4.0$ Vdc, $I_C = 0$)		I_{EBO}	—	25	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 30$ mAdc, $V_{CE} = 1.0$ Vdc)	 MPS3567, MPS3568 MPS3569	h_{FE}	 40 100	 — —	—
($I_C = 150$ mAdc, $V_{CE} = 1.0$ Vdc)	MPS3567, MPS3568 MPS3569		40 100	120 300	
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)		$V_{CE(sat)}$	—	0.25	Vdc
Base-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)		$V_{BE(sat)}$	—	1.1	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(1) ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)		f_T	60	—	MHz
Output Capacitance ($V_{CB} = 10$ V, f = 1.0 MHz)		C_{obo}	—	20	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)		C_{ibo}	—	80	pF

*Refer to MPS8098 for graphs for MPS3568.
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2

MPS3638
MPS3638A

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



SWITCHING TRANSISTOR

PNP SILICON

Refer to 2N4402 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Emitter Voltage	V_{CES}	25	Vdc
Collector-Base Voltage	V_{CBO}	25	Vdc
Emitter-Base Voltage	V_{EBO}	40	Vdc
Collector Current — Continuous	I_C	500	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	200	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 100 μAdc, V_{BE} = 0)		$V_{(BR)CES}$	25	—	Vdc
Collector-Emitter Sustaining Voltage(1) (I_C = 10 mAdc, I_B = 0)		$V_{CEO(sus)}$	25	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)		$V_{(BR)CBO}$	25	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current (V_{CE} = 15 Vdc, V_{BE} = 0) (V_{CE} = 15 Vdc, V_{BE} = 0, T_A = −65°C)		I_{CES}	 — —	 0.035 2.0	μAdc
Emitter Cutoff Current (V_{EB} = 3.0 V, I_C = 0)		I_{EBO}	—	35	nA
Base Current (V_{CE} = 15 Vdc, V_{BE} = 0)		I_B	—	0.035	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc)	MPS3638A	h_{FE}	80	—	—
(I_C = 10 mAdc, V_{CE} = 10 Vdc)	MPS3638 MPS3638A		20 100	— —	
(I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	MPS3638 MPS3638A		30 100	— —	
(I_C = 300 mAdc, V_{CE} = 2.0 Vdc)	MPS3638 MPS3638A		20 20	— —	
Collector-Emitter Saturation Voltage (I_C = 50 mAdc, I_B = 2.5 mAdc) (I_C = 300 mAdc, I_B = 30 mAdc)		$V_{CE(sat)}$	 — —	 0.25 1.0	Vdc
Base-Emitter Saturation Voltage (I_C = 50 mAdc, I_B = 2.5 mAdc) (I_C = 300 mAdc, I_B = 30 mAdc)		$V_{BE(sat)}$	 — 0.80	 1.1 2.0	Vdc

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (V_{CE} = 3.0 Vdc, I_C = 50 mAdc, f = 100 MHz)	MPS3638 MPS3638A	f_T	100 150	— —	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	MPS3638 MPS3638A	C_{obo}	— —	20 10	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	MPS3638 MPS3638A	C_{ibo}	— —	65 25	pF
Input Impedance (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{ie}	—	2000	Ohms
Voltage Feedback Ratio (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MPS3638 MPS3638A	h_{re}	— —	26 15	$X 10^{-4}$
Small-Signal Current Gain (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MPS3638 MPS3638A	h_{fe}	25 100	— —	—
Output Admittance (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{oe}	—	1.2	mmhos
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 10 Vdc, I_C = 300 mAdc, I_{B1} = 30 mAdc)	t_d	—	20	ns
Rise Time		t_r	—	70	ns
Storage Time	(V_{CC} = 10 Vdc, I_C = 300 mAdc, I_{B1} = 30 mAdc, I_{B2} = 30 mAdc)	t_s	—	140	ns
Fall Time		t_f	—	70	ns
Turn-On Time	(I_C = 300 mAdc, I_{B1} = 30 mAdc)	t_{on}	—	75	ns
Turn-Off Time	(I_C = 300 mAdc, I_{B1} = 30 mAdc, I_{B2} = 30 mAdc)	t_{off}	—	170	ns

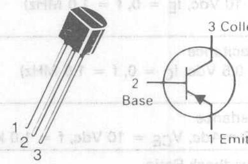
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	12	Vdc
Collector-Base Voltage	V_{CBO}	12	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	80	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



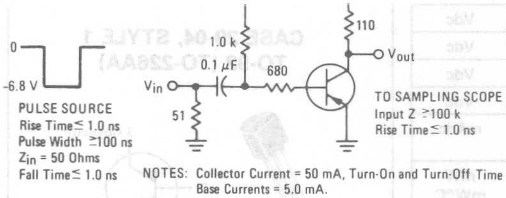
SWITCHING TRANSISTOR

PNP SILICON

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 100\ \mu Adc$, $V_{BE} = 0$)	$V_{(BR)CES}$	12	—	Vdc
Collector-Emitter Sustaining Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{CEO(sus)}$	12	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu Adc$, $I_E = 0$)	$V_{(BR)CBO}$	12	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu Adc$, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 6.0$ Vdc, $V_{BE} = 0$) ($V_{CE} = 6.0$ Vdc, $V_{BE} = 0$, $T_A = 65°C$)	I_{CES}	— —	0.01 1.0	μAdc
Base Current ($V_{CE} = 6.0$ Vdc, $V_{BE} = 0$)	I_B	—	10	nAdc
ON CHARACTERISTICS(1)				
DC Current Gain ($I_C = 10$ mAdc, $V_{CE} = 0.3$ Vdc) ($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	30 20	120 —	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc, $T_A = 65°C$)	$V_{CE(sat)}$	— — —	0.2 0.6 0.25	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 0.5$ mAdc) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)	$V_{BE(sat)}$	0.75 0.8 —	0.95 1.0 1.5	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc, f = 100 MHz)	f_T	500	—	MHz
Output Capacitance (V_{CB} = = 5.0 Vdc, $I_E = 0$, f = 1.0 MHz)	C_{obo}	—	3.5	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)	C_{ibo}	—	3.5	pF
SWITCHING CHARACTERISTICS				
Delay Time ($V_{CC} = 6.0$ Vdc, $I_C = 50$ mAdc, $V_{BE(off)} = 1.9$ Vdc, $I_{B1} = 5.0$ mAdc)	t_d	—	10	ns
Rise Time	t_r	—	30	ns
Storage Time ($V_{CC} = 6.0$ Vdc, $I_C = 50$ mAdc, $I_{B1} = I_{B2} = 5.0$ mAdc)	t_s	—	20	ns
Fall Time	t_f	—	12	ns
Turn-On Time ($V_{CC} = 6.0$ Vdc, $I_C = 50$ mAdc, $V_{BE(off)} = 1.9$ Vdc, $I_{B1} = 5.0$ mAdc) ($V_{CC} = 1.5$ Vdc, $I_C = 10$ mAdc, $I_{B1} = 0.5$ mAdc)	t_{on}	 — —	 25 60	ns
Turn-Off Time ($V_{CC} = 6.0$ Vdc, $I_C = 50$ mAdc, $V_{BE(off)} = 1.9$ V, $I_{B1} = I_{B2} = 5.0$ mAdc) ($V_{CC} = 1.5$ Vdc, $I_C = 10$ mAdc, $I_{B1} = I_{B2} = 0.5$ mAdc)	t_{off}	 — —	 35 75	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.



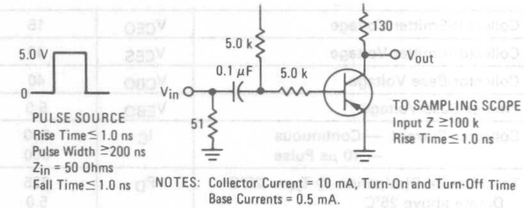


FIGURE 3 – DC CURRENT GAIN

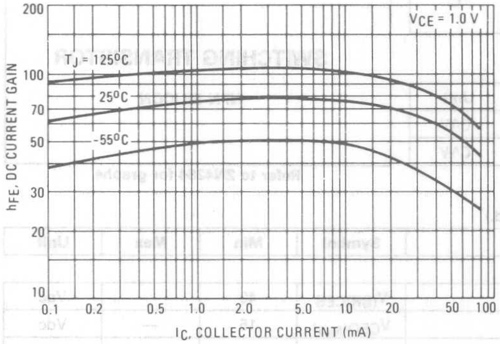


FIGURE 4 – "ON" VOLTAGES

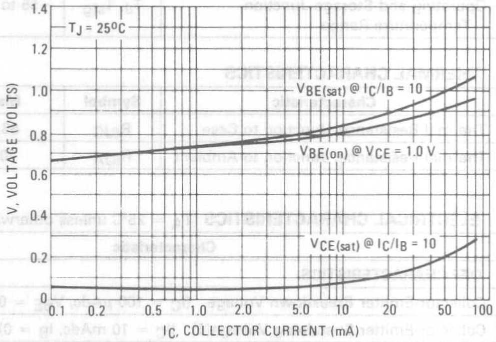


FIGURE 5 – COLLECTOR SATURATION REGION

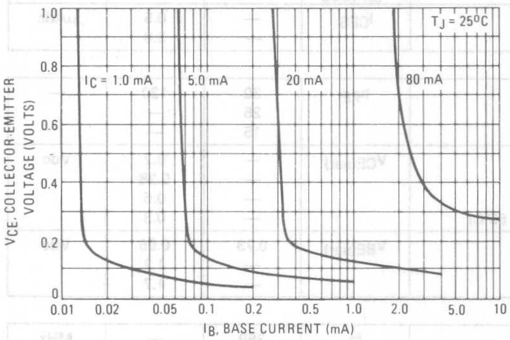


FIGURE 6 – TEMPERATURE COEFFICIENTS

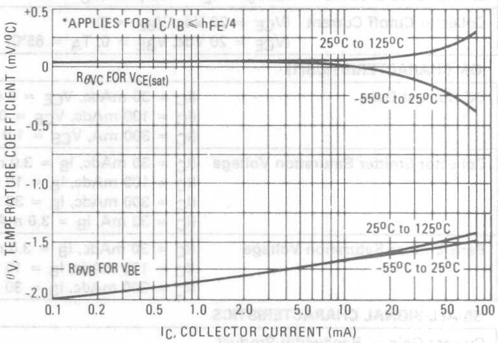


FIGURE 7 – CURRENT-GAIN–BANDWIDTH PRODUCT

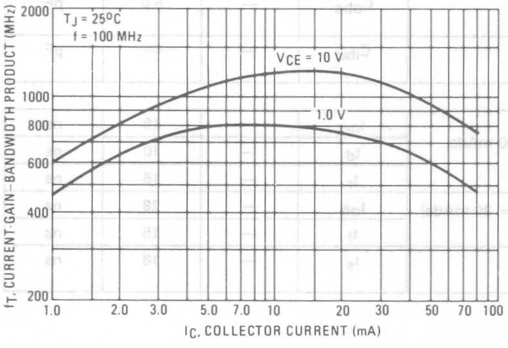
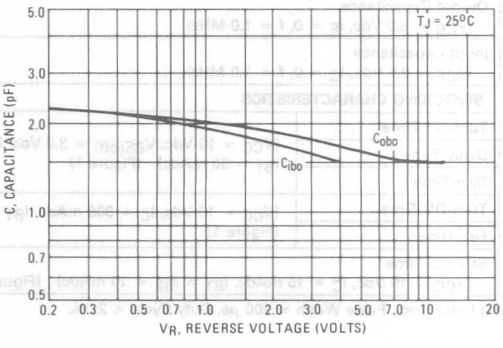


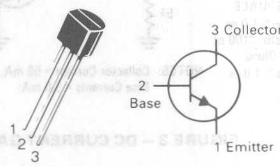
FIGURE 8 – CAPACITANCE



2

MPS3646

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



SWITCHING TRANSISTOR

NPN SILICON

Refer to 2N4264 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Emitter Voltage	V_{CES}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous — 10 μs Pulse	I_C	300 500	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12.0	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 100\ \mu Adc, V_{BE} = 0$)	$V_{(BR)CES}$	40	—	Vdc
Collector-Emitter Sustaining Voltage(1) ($I_C = 10\ mAdc, I_B = 0$)	$V_{CEO(sus)}$	15	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu Adc, I_E = 0$)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu Adc, I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 20\ Vdc, V_{BE} = 0$) ($V_{CE} = 20\ Vdc, V_{BE} = 0, T_A = 65°C$)	I_{CES}	— —	0.5 3.0	μAdc
ON CHARACTERISTICS(1)				
DC Current Gain ($I_C = 30\ mAdc, V_{CE} = 0.4\ Vdc$) ($I_C = 100\ mAdc, V_{CE} = 0.5\ Vdc$) ($I_C = 300\ mA, V_{CE} = 1.0\ Vdc$)	h_{FE}	30 25 15	120 — —	—
Collector-Emitter Saturation Voltage ($I_C = 30\ mAdc, I_B = 3.0\ mAdc$) ($I_C = 100\ mAdc, I_B = 10\ mAdc$) ($I_C = 300\ mAdc, I_B = 30\ mAdc$) ($I_C = 30\ mA, I_B = 3.0\ mA, T_A = 65°C$)	$V_{CE(sat)}$	— — — —	0.2 0.28 0.5 0.3	Vdc
Base-Emitter Saturation Voltage ($I_C = 30\ mAdc, I_B = 3.0\ mAdc$) ($I_C = 100\ mAdc, I_B = 10\ mAdc$) ($I_C = 300\ mAdc, I_B = 30\ mA$)	$V_{BE(sat)}$	0.73 — —	0.95 1.2 1.7	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 30\ mAdc, V_{CE} = 10\ Vdc, f = 100\ MHz$)	f_T	350	—	MHz
Output Capacitance ($V_{CB} = 5.0\ Vdc, I_E = 0, f = 1.0\ MHz$)	C_{obo}	—	5.0	pF
Input Capacitance ($V_{BE} = 0.5\ Vdc, I_C = 0, f = 1.0\ MHz$)	C_{ibo}	—	—	pF
SWITCHING CHARACTERISTICS				
Turn-On Time ($V_{CC} = 10\ Vdc, V_{BE(off)} = 3.0\ Vdc, I_C = 300\ mAdc, I_{B1} = 30\ mAdc$) (Figure 1)	t_{on}	—	18	ns
Delay Time ($V_{CC} = 10\ Vdc, V_{BE(off)} = 3.0\ Vdc, I_C = 300\ mAdc, I_{B1} = 30\ mAdc$) (Figure 1)	t_d	—	10	ns
Rise Time ($V_{CC} = 10\ Vdc, V_{BE(off)} = 3.0\ Vdc, I_C = 300\ mAdc, I_{B1} = 30\ mAdc$) (Figure 1)	t_r	—	15	ns
Turn-Off Time ($V_{CC} = 10\ Vdc, I_C = 300\ mAdc, I_{B1} = I_{B2} = 30\ mAdc$) (Figure 1)	t_{off}	—	28	ns
Fall Time ($V_{CC} = 10\ Vdc, I_C = 300\ mAdc, I_{B1} = I_{B2} = 30\ mAdc$) (Figure 1)	t_f	—	15	ns
Storage Time ($V_{CC} = 10\ Vdc, I_C = 10\ mAdc, I_{B1} = I_{B2} = 10\ mAdc$) (Figure 2)	t_s	—	18	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 – SWITCHING TIME TEST CIRCUIT

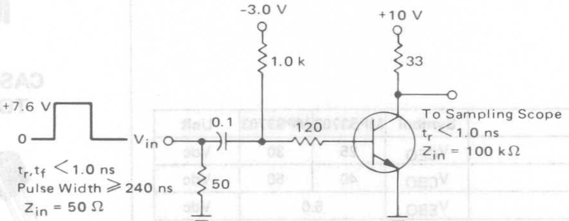
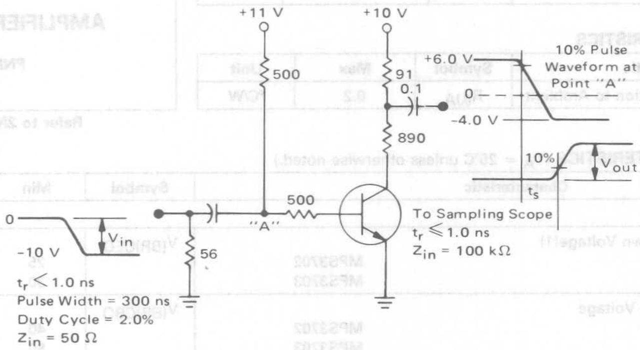
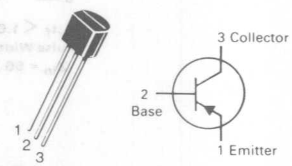


FIGURE 2 – CHARGE STORAGE TIME TEST CIRCUIT



MPS3702
MPS3703

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

PNP SILICON

Refer to 2N4402 for graphs.

MAXIMUM RATINGS

Rating	Symbol	MPS3702	MPS3703	Unit
Collector-Emitter Voltage	V_{CEO}	25	30	Vdc
Collector-Base Voltage	V_{CBO}	40	50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	600		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0		mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	0.2	°C/W

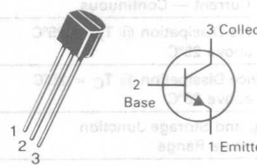
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	MPS3702 MPS3703	$V_{(BR)CEO}$	25 30	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	MPS3702 MPS3703	$V_{(BR)CBO}$	40 50	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$)		I_{CBO}	—	100	nAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)		I_{EBO}	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) ($I_C = 50$ mAdc, $V_{CE} = 5.0$ Vdc)	MPS3702 MPS3703	h_{FE}	60 30	300 150	—
Collector-Emitter Saturation Voltage(1) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)		$V_{CE(sat)}$	—	0.25	Vdc
Base-Emitter On Voltage(1) ($I_C = 50$ mAdc, $V_{CE} = 5.0$ Vdc)		$V_{BE(on)}$	0.6	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 5.0$ Vdc, f = 20 MHz)		f_T	100	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, f = 1.0 MHz)		C_{obo}	—	12	pF

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

MPS3704
MPS3705

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N4400 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	50	Vdc
Emitter-Base Voltage	V_{EBO}	5	Vdc
Collector Current — Continuous	I_C	600	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	0.2	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

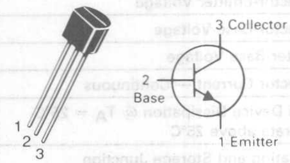
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_E = 0)		$V_{(BR)CEO}$	30	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)		$V_{(BR)CBO}$	50	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0)		I_{CBO}	—	100	nAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)		I_{EBO}	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 50 mAdc, V_{CE} = 2.0 Vdc)	MPS3704 MPS3705	h_{FE}	100 50	300 150	
Collector-Emitter Saturation Voltage(1) (I_C = 100 mAdc, I_B = 5.0 mAdc)	MPS3704 MPS3705	$V_{CE(sat)}$	— —	0.6 0.8	Vdc
Base-Emitter On Voltage(1) (I_C = 100 mAdc, V_{CE} = 2.0 Vdc)		$V_{BE(on)}$	0.5	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 2.0 V, f = 20 MHz)		f_T	100	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	12	pF

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

2

MPS3866

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	55	Vdc
Emitter-Base Voltage	V_{EBO}	3.5	Vdc
Collector Current — Continuous	I_C	0.4	Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

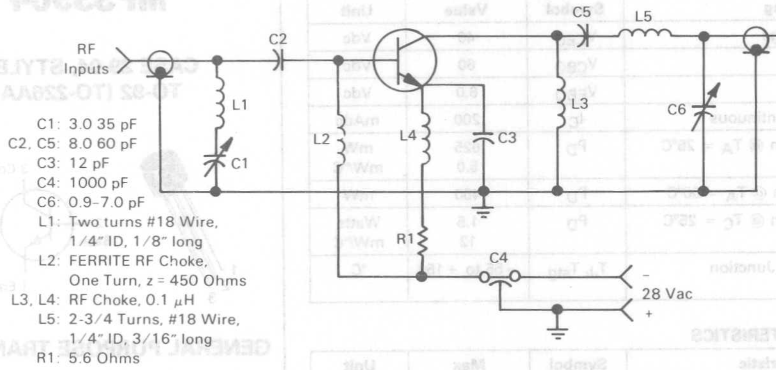
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 5.0 mAdc, R_{BE} = 10 Ω)	$V_{CER(sus)}$	55	—	Vdc
Collector-Emitter Sustaining Voltage (I_C = 5.0 mAdc, I_B = 0)	$V_{CEO(sus)}$	30	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	3.5	—	Vdc
Collector Cutoff Current (V_{CE} = 28 Vdc, I_B = 0)	I_{CEO}	—	0.02	mAdc
Collector Cutoff Current (V_{CE} = 30 Vdc, V_{BE} = −1.5 Vdc (Rev.), T_C = 150°C) (V_{CE} = 55 Vdc, V_{BE} = −1.5 Vdc (Rev.)	I_{CEX}	— —	5.0 0.1	mAdc
Emitter Cutoff Current (V_{BE} = 3.5 Vdc, I_C = 0)	I_{EBO}	—	0.1	mAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 360 mAdc, V_{CE} = 5.0 Vdc)(1) (I_C = 50 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}	5.0 10	— 200	
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 20 mAdc)	$V_{CE(sat)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 15 Vdc, f = 200 MHz)	f_T	500		MHz
Output Capacitance (V_{CB} = 28 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	3.0	pF
FUNCTIONAL TEST				
Amplifier Power Gain (V_{CC} = 28 Vdc, P_{out} = 1.0 W, f = 400 MHz)	G_{pe}	10	—	dB
Collector Efficiency (V_{CC} = 28 Vdc, P_{out} = 1.0 W, f = 400 MHz)	η	45	—	%

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

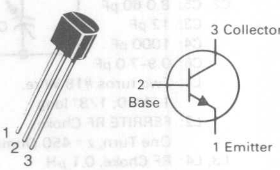
FIGURE 1 — 400 MHz TEST CIRCUIT SCHEMATIC



2

MPS3903
MPS3904

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Power Dissipation @ T_A = 60°C	P_D	450	mW
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)		$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current (V_{CE} = 30 Vdc, $V_{EB(off)}$ = 3.0 Vdc)		I_{CEX}	—	50	nAdc
Base Cutoff Current (V_{CE} = 30 Vdc, $V_{EB(off)}$ = 3.0 Vdc)		I_{BL}	—	50	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain		h_{FE}			—
(I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc)	MPS3903 MPS3904		20 40	— —	
(I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc)	MPS3903 MPS3904		35 70	— —	
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	MPS3903 MPS3904		50 100	150 300	
(I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	MPS3903 MPS3904		30 60	— —	
I_C = 100 mAdc, V_{CE} = 1.0 Vdc)	MPS3903 MPS3904		15 30	— —	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{CE(sat)}$	 — —	 0.2 0.3	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{BE(sat)}$	 0.65 —	 0.85 1.0	Vdc

Characteristic		Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	MPS3903 MPS3904	f_T	150 200	— —	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	4.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	8.0	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MPS3903 MPS3904	h_{ie}	0.5 1.0	8.0 10	kΩ
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MPS3903 MPS3904	h_{re}	0.1 0.5	5.0 8.0	$X\ 10^{-4}$
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MPS3903 MPS3904	h_{fe}	50 100	200 400	—
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{oe}	1.0	40	μmhos
Noise Figure (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 kΩ, f = 10 Hz to 15.7 kHz)	MPS3903 MPS3904	NF	— —	6.0 5.0	dB
SWITCHING CHARACTERISTICS					
Delay Time (V_{CC} = 3.0 Vdc, $V_{BE(off)}$ = 0.5 Vdc, I_C = 10 mAdc, I_{B1} = 1.0 mAdc)		t_d	—	35	ns
Rise Time (V_{CC} = 3.0 Vdc, $V_{BE(off)}$ = 0.5 Vdc, I_C = 10 mAdc, I_{B1} = 1.0 mAdc)		t_r	—	50	ns
Storage Time (V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)	MPS3903 MPS3904	t_s	— —	800 900	ns
Fall Time (V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)		t_f	—	90	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

EQUIVALENT SWITCHING TIME TEST CIRCUITS

FIGURE 1 – TURN-ON TIME

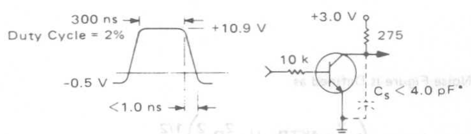
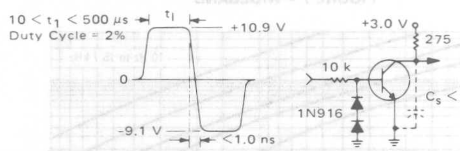


FIGURE 2 – TURN-OFF TIME



*Total shunt capacitance of test jig and connectors

TYPICAL NOISE CHARACTERISTICS
(V_{CE} = 5.0 Vdc, T_A = 25°C)

FIGURE 3 — NOISE VOLTAGE

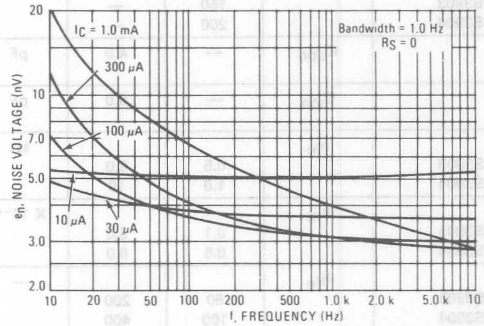
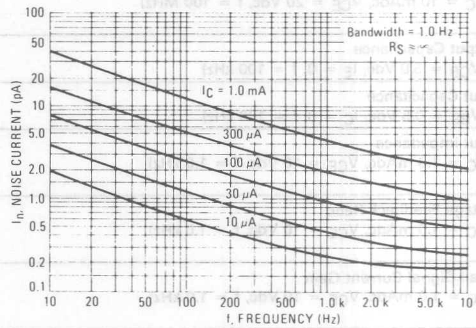


FIGURE 4 — NOISE CURRENT



NOISE FIGURE CONTOURS
(V_{CE} = 5.0 Vdc, T_A = 25°C)

FIGURE 5 — NARROW BAND, 100 Hz

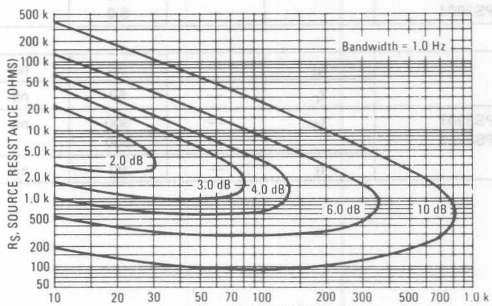


FIGURE 6 — NARROW BAND, 1.0 kHz

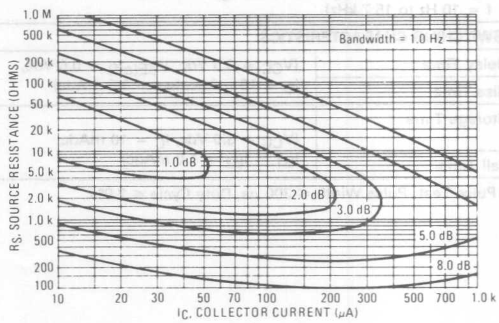
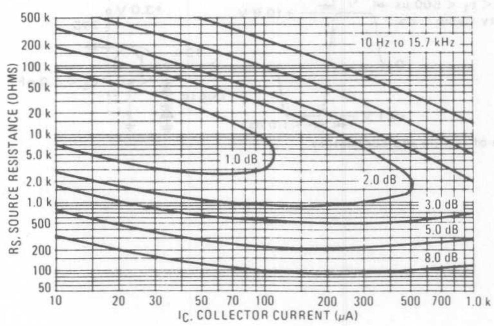


FIGURE 7 — WIDEBAND



Noise Figure is Defined as:

$$NF = 20 \log_{10} \left(\frac{e_n{}^2 + 4KTR_S + I_n{}^2 R_S{}^2}{4KTR_S} \right)^{1/2}$$

e_n = Noise Voltage of the Transistor referred to the input. (Figure 3)
I_n = Noise Current of the transistor referred to the input (Figure 4)
K = Boltzman's Constant (1.38 × 10^{-23} j/°K)
T = Temperature of the Source Resistance (°K)
R_S = Source Resistance (Ohms)

TYPICAL STATIC CHARACTERISTICS

FIGURE 8 — DC CURRENT GAIN

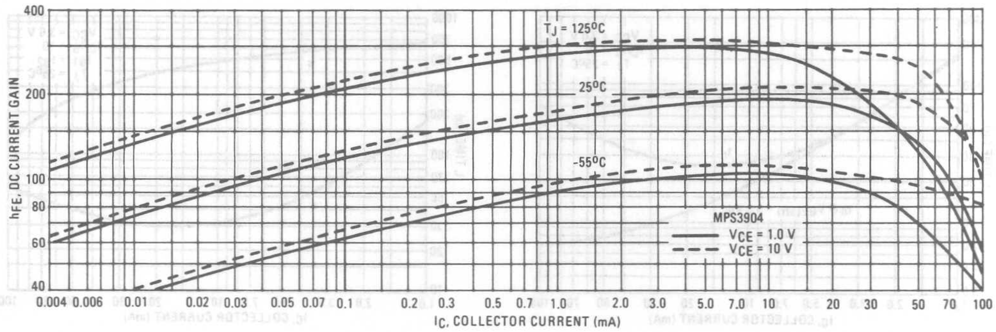


FIGURE 9 — COLLECTOR SATURATION REGION

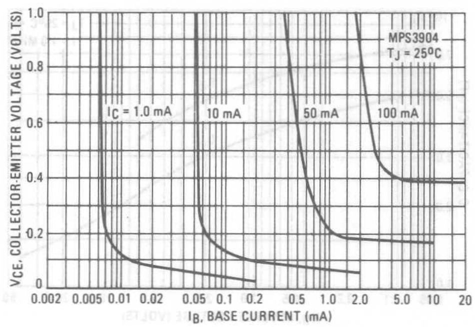


FIGURE 10 — COLLECTOR CHARACTERISTICS

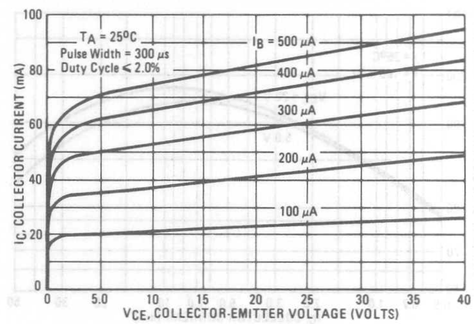


FIGURE 11 — "ON" VOLTAGES

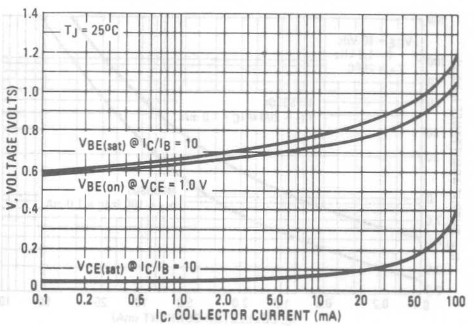
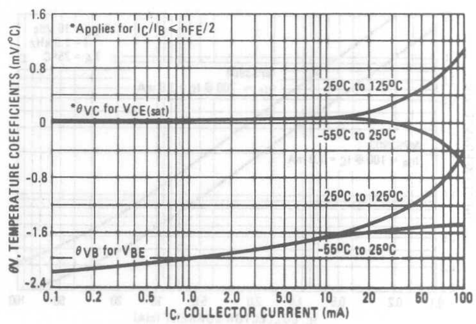


FIGURE 12 — TEMPERATURE COEFFICIENTS



TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 13 — TURN-ON TIME

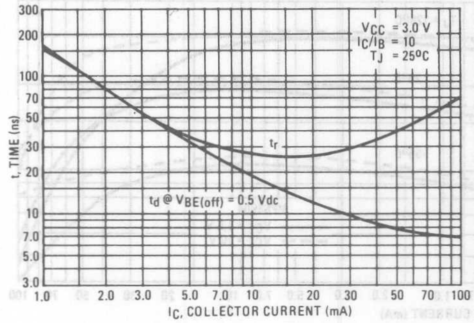


FIGURE 14 — TURN-OFF TIME

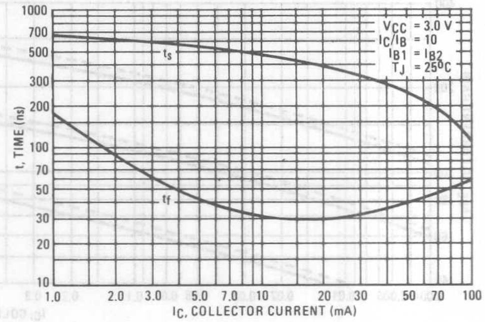


FIGURE 15 — CURRENT-GAIN — BANDWIDTH PRODUCT

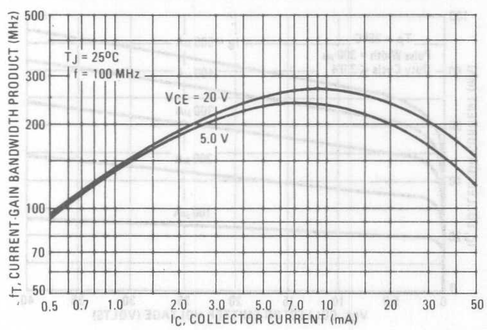


FIGURE 16 — CAPACITANCE

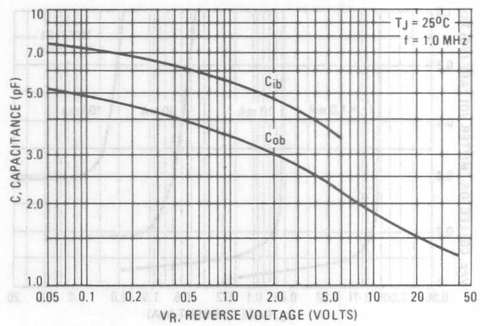


FIGURE 17 — INPUT IMPEDANCE

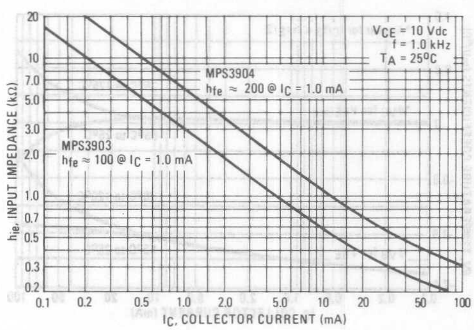
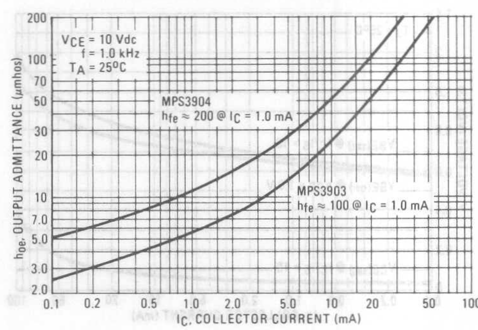


FIGURE 18 — OUTPUT ADMITTANCE



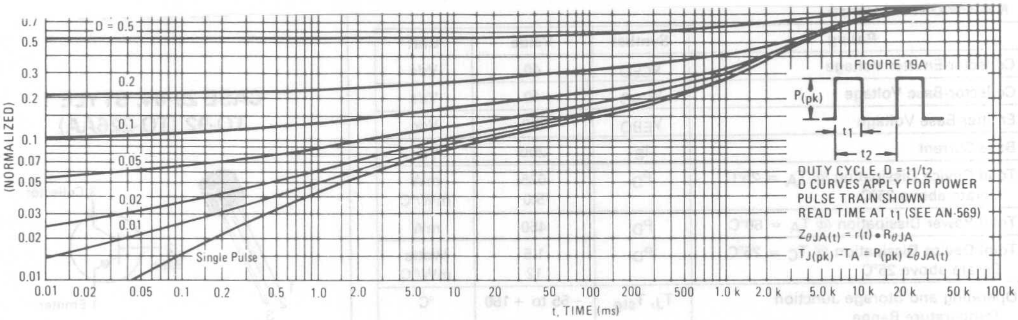


FIGURE 19A

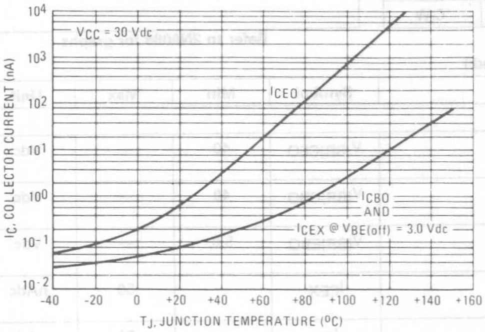
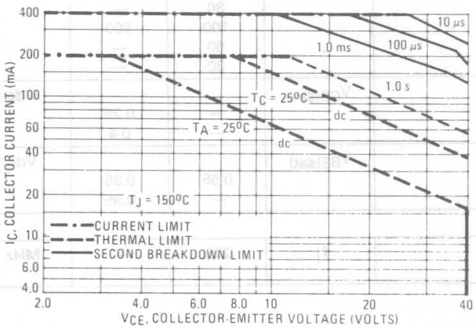


FIGURE 20



DESIGN NOTE: USE OF THERMAL RESPONSE DATA

A train of periodical power pulses can be represented by the model as shown in Figure 19A. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 19 was calculated for various duty cycles.

To find $Z_{\theta JA(t)}$, multiply the value obtained from Figure 19 by the steady state value $R_{\theta JA}$.

Example:

The MPS3903 is dissipating 2.0 watts peak under the following conditions:

$t_1 = 1.0$ ms, $t_2 = 5.0$ ms. (D = 0.2)

Using Figure 19 at a pulse width of 1.0 ms and D = 0.2, the reading of r(t) is 0.22.

The peak rise in junction temperature is therefore

$\Delta T = r(t) \times P_{(pk)} \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88^{\circ}C.$

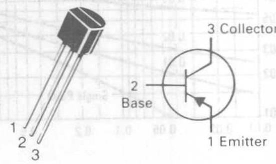
For more information, see AN-569.

The safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 20 is based upon $T_{J(pk)} = 150^{\circ}C$; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leqslant 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 19. At high case or ambient temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

MPS3906

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

Refer to 2N5086 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Base Current	I_B	200	Vdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Power Dissipation @ $T_A = 60°C$	P_D	450	mW
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 30$ Vdc, $V_{BE(off)} = 3.0$ Vdc)	I_{CEX}	—	50	nAdc
Base Cutoff Current ($V_{CE} = 30$ Vdc, $V_{BE(off)} = 3.0$ Vdc)	I_{BL}	—	50	nAdc
ON CHARACTERISTICS(1)				
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	 60 80 100 60 30	 — — 300 — —	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)	$V_{CE(sat)}$	 — —	 0.25 0.4	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)	$V_{BE(sat)}$	 0.65 —	 0.85 0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 20$ V, f = 100 MHz)	f_T	250	—	MHz

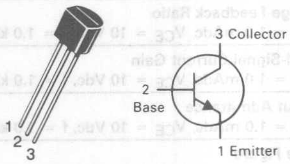
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	4.5	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	10	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{ie}	2.0	12	k ohms
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{re}	1.0	10	X 10^{-4}
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{fe}	100	400	—
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{oe}	3.0	60	μmhos
Noise Figure (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 k ohm, f = 10 Hz to 15.7 kHz)		NF	—	4.0	dB
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 3.0 Vdc, $V_{BE(off)}$ = 0.5 Vdc	t_d	—	35	ns
Rise Time	I_C = 10 mAdc, I_{B1} = 1.0 mAdc)	t_r	—	50	ns
Storage Time	(V_{CC} = 3.0 Vdc, I_C = 10 mAdc,	t_s	—	600	ns
Fall Time	I_{B1} = I_{B2} = 1.0 mAdc)	t_f	—	90	ns

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

MPS4123
MPS4124

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR
NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	MPS4123	MPS4124	Unit
Collector-Emitter Voltage	V_{CE}	30	25	Vdc
Collector-Base Voltage	V_{CB}	40	30	Vdc
Emitter-Base Voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
Total Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Power Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12		W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

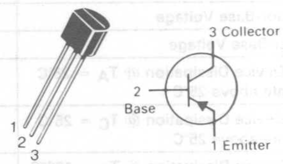
ELECTRICAL CHARACTERISTICS ($T_C = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mA, $I_B = 0$)	MPS4123 MPS4124	$V_{(BR)CEO}$	30 25	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μA, $I_E = 0$)	MPS4123 MPS4124	$V_{(BR)CBO}$	40 30	— —	Vdc
Emitter-Base Breakdown Voltage ($I_C = 0$, $I_E = 10$ μA)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 20$ V, $I_E = 0$)		I_{CBO}	—	50	nAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ V, $I_C = 0$)		I_{EBO}	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 2.0$ mA, $V_{CE} = 1.0$ V) ($I_C = 50$ mA, $V_{CE} = 1.0$ V)	 MPS4123 MPS4124 MPS4123 MPS4124	h_{FE}	 50 120 25 60	 150 360 — —	—
Collector-Emitter Saturation Voltage ($I_C = 50$ mA, $I_B = 5.0$ mA)		$V_{CE(sat)}$	—	0.3	Vdc
Base-Emitter Saturation Voltage ($I_C = 50$ mA, $I_B = 5.0$ mA)		$V_{BE(sat)}$	—	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 10$ mA, $V_{CE} = 20$ V, f = 100 MHz)	MPS4123 MPS4124	f_T	100 170	— —	MHz
Output Capacitance ($V_{CB} = 5.0$ V, $I_E = 0$, f = 100 kHz)		C_{ob}	—	4.0	pF
Input Capacitance ($V_{BE} = 0.5$ V, $I_C = 0$, f = 100 kHz)	MPS4123 MPS4124	C_{ib}	— —	14 13.5	pF
Small-Signal Current Gain ($I_C = 2.0$ mA, $V_{CE} = 1.0$ V, f = 1.0 kHz)	MPS4123 MPS4124	h_{fe}	50 120	200 480	—
Noise Figure ($I_C = 100$ μA, $V_{CE} = 5.0$ V, $R_S = 1.0$ kΩ, Noise Bandwidth = 10 Hz to 15.7 kHz)	 MPS4123 MPS4124	NF	 — —	 6.0 5.0	dB

MPS4125
MPS4126

CASE 29-04, STYLE 1
TO-92 (TO-226AA)

2



AMPLIFIER TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	MPS4125	MPS4126	Unit
Collector-Emitter Voltage	V_{CE}	30	25	Vdc
Collector-Base Voltage	V_{CB}	30	25	Vdc
Emitter-Base Voltage	V_{EB}	4.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
Total Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Power Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12		W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

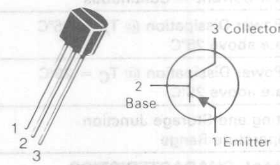
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mA, $I_B = 0$)	MPS4125 MPS4126	$V_{(BR)CEO}$	30 25	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu A$, $I_E = 0$)	MPS4125 MPS4126	$V_{(BR)CBO}$	30 25	— —	Vdc
Emitter-Base Breakdown Voltage ($I_C = 0$, $I_E = 10\ \mu A$)		$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 20$ V, $I_E = 0$)		I_{CBO}	—	50	nAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ V, $I_C = 0$)		I_{EBO}	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 2.0$ mA, $V_{CE} = 1.0$ V) ($I_C = 50$ mA, $V_{CE} = 1.0$ V)	 MPS4125 MPS4126 MPS4125 MPS4126	h_{FE}	 50 120 25 60	 150 360 — —	—
Collector-Emitter Saturation Voltage ($I_C = 50$ mA, $I_B = 5.0$ mA)		$V_{CE(sat)}$	—	0.4	Vdc
Base-Emitter Saturation Voltage ($I_C = 50$ mA, $I_B = 5.0$ mA)		$V_{BE(sat)}$	—	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 10$ mA, $V_{CE} = 20$ V, f = 100 MHz)	MPS4125 MPS4126	f_T	150 170	— —	MHz
Output Capacitance ($V_{CB} = 5.0$ V, $I_E = 0$, f = 100 kHz)		C_{ob}	—	4.5	pF
Input Capacitance ($V_{BE} = 0.5$ V, $I_C = 0$, f = 100 kHz)	MPS4125 MPS4126	C_{ib}	— —	12 11.5	pF
Small-Signal Current Gain ($I_C = 2.0$ mA, $V_{CE} = 1.0$ V, f = 1.0 kHz)	MPS4125 MPS4126	h_{fe}	50 120	200 480	—
Noise Figure ($I_C = 100\ \mu A$, $V_{CE} = 5.0$ V, $R_S = 1.0$ kΩ, Noise Bandwidth = 10 Hz to 15.7 kHz)	MPS4125 MPS4126	NF	— —	5.0 4.0	dB

MPS4249
MPS4250
MPS4250A

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	MPS4250	MPS4249 MPS4250A	Unit
Collector-Emitter Voltage	V_{CEO}	40	60	Vdc
Collector-Emitter Voltage	V_{CES}	40	60	Vdc
Collector-Base Voltage	V_{CBO}	40	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	5.0	Vdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	1.5 12	mW mW/°C
Total Device Dissipation @ $T_C = 100°C$ Derate above 100°C	P_D			
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +125		°C
Junction Temperature	T_J	125		°C
Lead Temperature (10 seconds)	T_L	260		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 μA) (I_C = 5.0 mA) (I_C = 5.0 mA)	 MPS4249 MPS4250 MPS4250A	$V_{(BR)CES}$	 60 40 60	 — — —	Vdc
Collector-Emitter Sustaining Voltage(1) (I_C = 5.0) (I_C = 5.0)	 MPS4250 MPS4249, MPS4250A	$V_{(BR)CEO(sus)}$	 40 60	 — —	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μA) (I_C = 10 μA)	 MPS4250 MPS4249, MPS4250A	$V_{(BR)CBO}$	 40 60	 — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μA)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 40 V) (V_{CB} = 50 V) (V_{CB} = 40 V, T_A = 65°C)	 MPS4249, MPS4250A MPS4250 MPS4249, MPS4250	I_{CBO}	 — — —	 10 10 3.0	nA
Emitter Cutoff Current (V_{BE} = 3.0 V)		I_{EBO}		20	nA
ON CHARACTERISTICS					
DC Current Gain (I_C = 100 μA, V_{CE} = 5.0 V) (I_C = 100 μA, V_{CE} = 5.0 V) (I_C = 1.0 mA, V_{CE} = 5.0 V) (I_C = 1.0 mA, V_{CE} = 5.0 V) (I_C = 10 mA, V_{CE} = 5.0 V) (I_C = 10 mA, V_{CE} = 5.0 V)	 MPS4249 MPS4250,A MPS4249 MPS4250 MPS4249 MPS4250	h_{FE}	 100 250 100 250 100 250	 300 700 — — — —	
Collector-Emitter Saturation Voltage(1) (I_C = 10 mA, I_B = 0.5 mA)		$V_{CE(sat)}$	—	0.25	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 10 mA, I_B = 0.5 mA)		$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance (V_{CB} = 5.0 V, f = 1.0 MHz)		C_{obo}	—	6.0	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Input Capacitance (V_{BE} = 0.5 V, f = 1.0 MHz)		C_{ibo}	—	16	pF
Small-Signal Current Gain		h_{fe}			—
(I_C = 1.0 mA, V_{CE} = 5.0 V, f = 1.0 kHz)	MPS4249		100	500	
(I_C = 1.0 mA, V_{CE} = 5.0 V, f = 1.0 kHz)	MPS4250,A		250	800	
(I_C = 0.5 mA, V_{CE} = 5.0 V, f = 20 MHz)	MPS4249,50		2.0	—	
Noise Figure		NF			dB
(I_C = 20 μA, V_{CE} = 5.0 V, R_S = 10 kΩ, f = 1.0 kHz, P_{BW} = 150 Hz)	MPS4250,A		—	2.0	
(I_C = 20 μA, V_{CE} = 5.0 V, R_S = 10 kΩ, f = 1.0 kHz, P_{BW} = 150 Hz)	MPS4249		—	3.0	
(I_C = 250 μA, V_{CE} = 5.0 V, R_S = 1.0 kΩ, f = 1.0 kHz, P_{BW} = 150 Hz)	MPS4250,A		—	2.0	
(I_C = 250 μA, V_{CE} = 5.0 V, R_S = 1.0 kΩ, f = 1.0 kHz, P_{BW} = 150 Hz)	MPS4249		—	3.0	

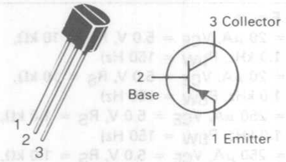
(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	12	Vdc
Collector-Base Voltage	V_{CBO}	12	Vdc
Emitter-Base Voltage	V_{EBO}	4.5	Vdc
Collector Current — Continuous	I_C	80	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 12	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



SWITCHING TRANSISTOR

PNP SILICON

Refer to MPS3640 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

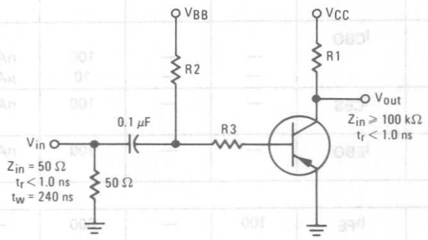
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 100\ \mu Adc$, $V_{BE} = 0$)	$V_{(BR)CES}$	12	—	Vdc
Collector-Emitter Sustaining Voltage(1) ($I_C = 3.0$ mAdc, $I_B = 0$)	$V_{CEO(sus)}$	12	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu Adc$, $I_E = 0$)	$V_{(BR)CBO}$	12	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu Adc$, $I_C = 0$)	$V_{(BR)EBO}$	4.5	—	Vdc
Collector Cutoff Current ($V_{CE} = 6.0$ Vdc, $V_{BE} = 0$) ($V_{CE} = 6.0$ Vdc, $V_{BE} = 0$, $T_A = +65°C$)	I_{CES}	 — —	 0.01 5.0	μAdc
ON CHARACTERISTICS(1)				
DC Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 0.5$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 3.0$ Vdc) ($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	 15 30 30	 — 120 —	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)	$V_{CE(sat)}$	 — —	 0.15 0.5	Vdc
Base-Emitter On Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)	$V_{BE(sat)}$	 0.75 —	 0.95 1.5	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product(2) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	700	—	MHz
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)	C_{ibo}	—	3.5	pF
Collector-Base Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{cb}	—	3.0	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS					
Turn-On Time	(V_{CC} = 1.5 Vdc, $V_{BE(off)}$ = 0, I_C = 10 mAdc, I_{B1} = 1.0 mAdc)	t_{on}	—	15	ns
Delay Time		t_d	—	10	ns
Rise Time		t_r	—	15	ns
Turn-Off Time	(V_{CC} = 1.5 Vdc, I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)	t_{off}	—	20	ns
Storage Time		t_s	—	20	ns
Fall Time		t_f	—	10	ns
Storage Time ($I_C \approx$ 10 mAdc, $I_{B1} \approx$ 10 mAdc, $I_{B2} \approx$ 10 mAdc)		t_s	—	20	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

FIGURE 1 — SWITCHING TIME TEST CIRCUIT



	V_{in} Volts	V_{BB} Volts	V_{CC} Volts	R1 Ohms	R2 Ohms	R3 Ohms	I_C mA	I_{B1} mA	I_{B2} mA
t_{on}	-5.8	GND	-1.5	130	2.2 k	5 k	10	1.0	–
t_{off}	+9.8	-8.0	-1.5	130	2.2 k	5 k	10	1.0	1.0
t_s	+9.0	-10	-3.0	270	510	390	10	10	10

MAXIMUM RATINGS

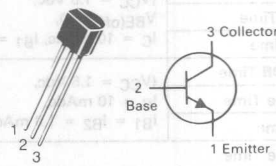
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	25	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	100	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

MPS5172

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MPS3903 for graphs.

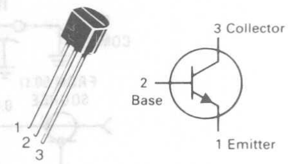
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	25	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 25$ Vdc, $I_E = 0$) ($V_{CB} = 25$ Vdc, $I_E = 0$, $T_A = 100°C$)	I_{CBO}	— —	— —	100 10	nAdc μAdc
Collector Cutoff Current ($V_{CE} = 25$ Vdc, $V_{BE} = 0$)	I_{CES}	—	—	100	nAdc
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	100	—	500	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	—	0.25	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	—	0.75	—	Vdc
Base-Emitter On Voltage ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc)	$V_{BE(on)}$	0.5	—	1.2	Vdc
SMALL SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 2.0$ mAdc, $V_{CE} = 5.0$ Vdc)	f_T	—	120	—	MHz
Collector-Base Capacitance ($V_{CB} = 0$, $I_E = 0$, f = 1.0 MHz)	C_{cb}	1.6	—	10	pF
Small Signal Current Gain ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	100	—	750	—

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MPS5179

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



HIGH FREQUENCY TRANSISTOR

NPN SILICON

2

MAXIMUM RATINGS

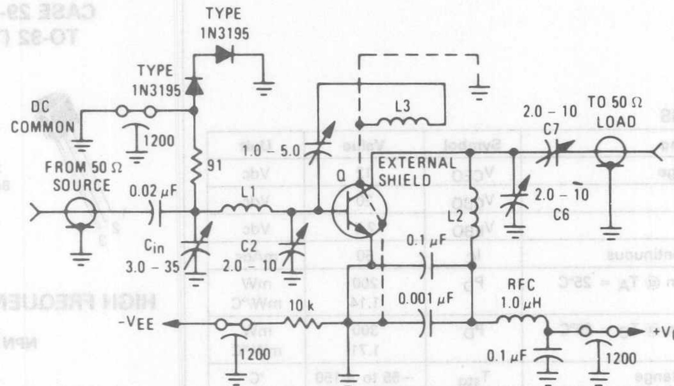
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	12	Vdc
Collector-Base Voltage	V_{CBO}	20	Vdc
Emitter-Base Voltage	V_{EBO}	2.5	Vdc
Collector Current — Continuous	I_C	50	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	200 1.14	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	300 1.71	mW mW/°C
Storage Temperature Range	T_{stg}	−55 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (I_C = 3.0 mAdc, I_B = 0)	$V_{CEO(sus)}$	12	—	Vdc
Collector-Base Breakdown Voltage (I_C = 0.001 mAdc, I_E = 0)	$V_{(BR)CBO}$	20	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 0.01 mAdc, I_C = 0)	$V_{(BR)EBO}$	2.5	—	Vdc
Collector Cutoff Current (V_{CB} = 15 Vdc, I_E = 0) (V_{CB} = 15 Vdc, I_E = 0, T_A = 150°C)	I_{CBO}	 — —	 0.02 1.0	μAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 3.0 mAdc, V_{CE} = 1.0 Vdc)	h_{FE}	25	250	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{CE(sat)}$	—	0.4	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{BE(sat)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product(1) (I_C = 5.0 mAdc, V_{CE} = 6.0 Vdc, f = 100 MHz)	f_T	900	2000	MHz
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 0.1 to 1.0 MHz)	C_{cb}	—	1.0	pF
Small Signal Current Gain (I_C = 2.0 mAdc, V_{CE} = 6.0 Vdc, f = 1.0 kHz)	h_{fe}	25	300	—
Collector Base Time Constant (I_E = 2.0 mAdc, V_{CB} = 6.0 Vdc, f = 31.9 MHz)	$r_b'C_c$	3.0	14	ps
Noise Figure (See Figure 1) (I_C = 1.5 mAdc, V_{CE} = 6.0 Vdc, R_S = 50 ohms, f = 200 MHz)	NF	—	4.5	dB
Common-Emitter Amplifier Power Gain (See Figure 1) (V_{CE} = 6.0 Vdc, I_C = 5.0 mAdc, f = 200 MHz)	G_{pe}	15	—	dB

(1) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

FIGURE 1 — 200 MHz AMPLIFIER POWER GAIN AND NOISE FIGURE CIRCUIT

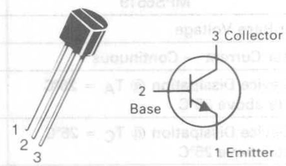


L1 1-3/4 Turns, #18 AWG, 0.5″ L, 0.5″ Diameter
L2 2 Turns, #16 AWG, 0.5″ L, 0.5″ Diameter
L3 2 Turns, #13 AWG, 0.25″ L, 0.5″ Diameter (Position 1/4″ from L2)

2

MPS6507

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	20	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	100	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	200	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

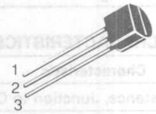
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	20	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	30	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_E = 0$) ($V_{CB} = 15$ Vdc, $I_E = 0$, $T_A = 60°C$)	I_{CBO}	 — —	 — —	 50 1.0	 nAdc μAdc
ON CHARACTERISTICS					
DC Current Gain(2) ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	25	75	—	—
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	700	800	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	1.25	2.5	pF
Small-Signal Current Gain ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc, f = 44 MHz)	h_{fe}	20	—	—	—

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2

NPN
MPS6512 thru MPS6515
PNP
MPS6516 thru MPS6519

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

Refer to 2N4125 for graphs.

MAXIMUM RATINGS

Rating	Symbol	NPN	PNP	Unit
Collector-Emitter Voltage	V_{CEO}			Vdc
MPS6512, MPS6513		30	—	
MPS6514, MPS6515		25	—	
MPS6516 thru MPS6518		—	40	
MPS6519		—	25	
Collector-Base Voltage	V_{CBO}			Vdc
MPS6512 thru MPS6515		40	—	
MPS6516 thru MPS6518		—	40	
MPS6519		—	25	
Emitter-Base Voltage	V_{EBO}	4.0	4.0	Vdc
Collector Current — Continuous	I_C	100	100	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$				Vdc
($I_C = 0.5$ mAdc, $I_B = 0$)	MPS6512, MPS6513		30	—	—	
	MPS6514, MPS6515		25	—	—	
($I_C = 0.5$ mAdc, $I_B = 0$)	MPS6516 thru MPS6518		40	—	—	
	MPS6519		25	—	—	
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	4.0	—	—	Vdc
($I_E = 10$ μAdc, $I_C = 0$)			4.0	—	—	
Collector Cutoff Current		I_{CBO}				μAdc
($V_{CB} = 30$ Vdc, $I_E = 0$)			—	—	0.05	
($V_{CB} = 30$ Vdc, $I_E = 0$)	MPS6516 thru MPS6518		—	—	0.05	
($V_{CB} = 20$ Vdc, $I_E = 0$)	MPS6519		—	—	0.05	
ON CHARACTERISTICS						
DC Current Gain		h_{FE}				—
($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc)	MPS6512		50	—	100	
	MPS6513		90	—	180	
	MPS6514		150	—	300	
	MPS6515		250	—	500	
($I_C = 100$ mAdc, $V_{CE} = 10$ Vdc)(1)	MPS6512		30	—	—	
	MPS6513		60	—	—	
	MPS6514		90	—	—	
	MPS6515		150	—	—	
($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc)	MPS6516		50	—	100	
	MPS6517		90	—	180	
	MPS6518		150	—	300	
	MPS6519		250	—	500	
($I_C = 100$ mAdc, $V_{CE} = 10$ Vdc)(1)	MPS6516		30	—	—	
	MPS6517		60	—	—	
	MPS6518		90	—	—	
	MPS6519		150	—	—	
Collector-Emitter Saturation Voltage ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)		$V_{CE(sat)}$	—	—	0.5	Vdc
($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)			—	—	0.5	
SMALL-SIGNAL CHARACTERISTICS						
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)		C_{obo}	—	—	3.5	pF
($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)			—	—	4.0	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

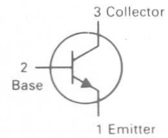
MAXIMUM RATINGS

Rating	Symbol	NPN	PNP	Unit
Collector-Emitter Voltage	V_{CEO}			Vdc
MPS6520, MPS6521		25	—	
MPS6523		—	25	
Collector-Base Voltage	V_{CBO}			Vdc
MPS6520, MPS6521		40	—	
MPS6523		—	25	
Emitter-Base Voltage	V_{EBO}	4.0		Vdc
Collector Current — Continuous	I_C	100		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

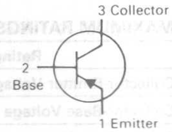
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient (Printed Circuit Board Mounting)	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

NPN MPS6520 MPS6521



PNP MPS6523



CASE 29-04, STYLE 1
TO-92 (TO-226AA)

AMPLIFIER TRANSISTOR

Refer to MPS3903 for NPN graphs.*

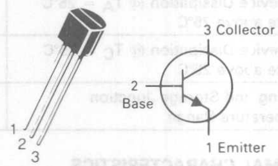
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$			Vdc
(I_C = 0.5 mAdc, I_B = 0)		25	—	
(I_C = 0.5 mAdc, I_B = 0)		25	—	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$			Vdc
(I_E = 10 μAdc, I_C = 0)		4.0	—	
(I_E = 10 μAdc, I_C = 0)		4.0	—	
Collector Cutoff Current	I_{CBO}			μAdc
(V_{CB} = 30 Vdc, I_E = 0)		—	0.05	
(V_{CB} = 20 Vdc, I_E = 0)		—	0.05	
ON CHARACTERISTICS				
DC Current Gain	h_{FE}		—	—
(I_C = 100 μAdc, V_{CE} = 10 Vdc) MPS6520		100	—	
MPS6521		150		
			400	
(I_C = 2.0 mAdc, V_{CE} = 10 Vdc) MPS6520		200	600	
MPS6521		300		
			—	
(I_C = 100 μAdc, V_{CE} = 10 Vdc) MPS6523		150		
			400	
(I_C = 2.0 mAdc, V_{CE} = 10 Vdc) MPS6523		300		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			Vdc
(I_C = 50 mAdc, I_B = 5.0 mAdc)		—	0.5	
(I_C = 50 mAdc, I_B = 5.0 mAdc)		—	0.5	
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance	C_{obo}			pF
(V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		—	3.5	
(V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		—	3.5	
Noise Figure	NF			dB
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 kohms, Power Bandwidth = 15.7 kHz, 3.0 dB points @ 10 Hz and 10 kHz)		—	3.0	
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 kohms, Power Bandwidth = 15.7 kHz, 3.0 dB points @ 10 Hz and 10 kHz)		—	3.0	

*Refer to 2N5086 for PNP graphs.

MPS6530
MPS6531

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N4400 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	600	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625	mW
Junction Temperature	T_J, T_{stg}	150	°C

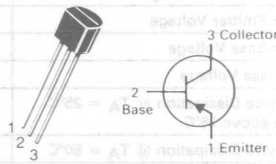
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	0.2	°C/mW

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$			Vdc
($I_B = 10\ \mu$Adc, $I_C = 0$)		5.0	—	
($I_B = 10\ \mu$Adc, $I_C = 0$)		4.0	—	
Collector Cutoff Current	I_{CBO}			μAdc
($V_{CB} = 40$ Vdc, $I_E = 0$)		—	0.05	
($V_{CB} = 40$ Vdc, $I_E = 0$, $T_A = 60°C$)		—	2.0	
ON CHARACTERISTICS				
DC Current Gain	h_{FE}			—
($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc) MPS6530		30	—	
MPS6531		60	—	
($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc) MPS6530		40	120	
MPS6531		90	270	
($I_C = 500$ mAdc, $V_{CE} = 10$ Vdc) MPS6530		25	—	
MPS6531		50	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			Vdc
($I_C = 100$ mAdc, $I_B = 10$ mAdc) MPS6530		—	0.5	
MPS6531		—	0.3	
Base-Emitter Saturation Voltage ($I_C = 100$ mAdc, $I_B = 10$ mAdc)	$V_{BE(sat)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance	C_{obo}			pF
($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)		—	5.0	
($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)		—	7.0	

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

PNP SILICON

Refer to 2N4402 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	600	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625	mW
Junction Temperature	T_J, T_{stg}	150	°C

THERMAL CHARACTERISTICS

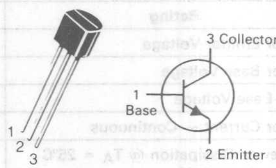
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	0.2	°C/mW

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage (I_B = 10 μAdc, I_C = 0) (I_B = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	 5.0 4.0	 — —	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0) (V_{CB} = 30 Vdc, I_E = 0, T_A = 60°C) (V_{CB} = 20 Vdc, I_E = 0, T_A = 60°C)	I_{CBO}	 — — —	 0.05 2.0 —	μAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 10 mAdc, V_{CE} = 1.0 Vdc) (I_C = 100 mAdc, V_{CE} = 1.0 Vdc) (I_C = 500 mAdc, V_{CE} = 10 Vdc)	h_{FE}	 60 90 50	 — 270 —	—
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 10 mAdc)	$V_{CE(sat)}$		0.3	Vdc
Base-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 10 mAdc)	$V_{BE(sat)}$		1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz) (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	 — —	 5.0 7.0	pF

MPS6544

CASE 29-04, STYLE 2
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MPSH20 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	45	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.81	mW mW/°C
Total Device Dissipation @ T_A = 60°C	P_D	210	mW
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +135	°C

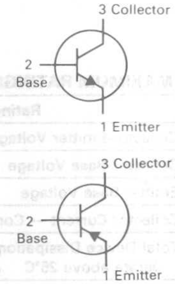
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_E = 0)	$V_{(BR)CEO}$	45	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current (V_{CB} = 35 Vdc, I_E = 0)	I_{CBO}	—	0.5	μAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 30 mAdc, V_{CE} = 10 Vdc)	h_{FE}	20	—	—
Collector-Emitter Saturation Voltage (I_C = 30 mAdc, I_B = 3.0 mAdc)	$V_{CE(sat)}$	—	0.5	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Common-Emitter Reverse Transfer Capacitance (V_{CB} = 10 Vdc, I_C = 0, f = 100 kHz)	C_{re}	—	0.65	pF
Output Admittance (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 45 MHz)	y_{oe}	—	0.10	mmhos
Output Voltage ($V_{in(RMS)}$ = 12 mV, f = 45 MHz)	V_{out}	1.0	—	Vdc

NPN MPS6560
PNP MPS6562



CASE 29-04, STYLE 1
TO-92 (TO-226AA)

AUDIO TRANSISTOR

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	25	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	500	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	200	°C/mW

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

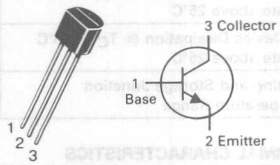
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	25	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	25	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 25$ Vdc, $I_B = 0$)	I_{CEO}	—	100	nAdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$)	I_{CBO}	—	100	nAdc
Emitter Cutoff Current ($V_{EB(off)} = 4.0$ Vdc, $I_C = 0$)	I_{EBO}	—	100	nAdc
ON CHARACTERISTICS(2)				
DC Current Gain ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 500$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	 35 50 50	 — — 200	—
Collector-Emitter Saturation Voltage ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter On Voltage ($I_C = 500$ mAdc, $V_{CE} = 1.0$ Vdc)	$V_{BE(on)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 30 MHz)	f_T	60	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	30	pF

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

thru
MPS6570A

CASE 29-04, STYLE 2
TO-92 (TO-226AA)



VHF TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	20	Vdc
Collector-Base Voltage	V_{CBO}	20	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	50	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case(1)	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)		$V_{(BR)CEO}$	20	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)		$V_{(BR)CBO}$	20	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	3.0	—	Vdc
Collector Cutoff Current (V_{CB} = 10 Vdc, I_C = 0)		I_{CBO}	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 4.0 mAdc, V_{CE} = 5.0 Vdc)		h_{FE}	20	200	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 5.0 mAdc)		$V_{CE(sat)}$	0.1	3.0	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 5.0 mAdc)		$V_{BE(sat)}$	—	0.96	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 4.0 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	MPS6568A MPS6569A, MPS6570A	f_T	375 300	800 800	MHz
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz, emitter guarded)	MPS6568A/6570A	C_{cb}	—	0.65	pF
Noise Figure (V_{AGC} = 1.4 Vdc, R_S = 50 ohms, f = 200 MHz) (V_{AGC} = 2.75 Vdc, R_S = 50 ohms, f = 45 MHz)	MPS6568A MPS6569A, MPS6570A	NF	— —	3.3 6.0	dB
FUNCTIONAL TEST					
Amplifier Power Gain (V_{AGC} = 1.4 Vdc, R_S = 50 ohms, f = 200 MHz) (V_{AGC} = 2.75 Vdc, R_S = 50 ohms, f = 45 MHz)	MPS6568A MPS6569A, MPS6570A	G_{pe}	20 22.5	27 28.5	dB
Forward AGC Voltage (Gain Reduction = 30 dB, R_S = 50 ohms, f = 200 MHz) (Gain Reduction = 30 dB, R_S = 50 ohms, f = 45 MHz)	MPS6568A MPS6569A MPS6570A	V_{AGC}	4.0 4.4 5.2	5.0 5.4 6.2	Vdc

FIGURE 1 — POWER GAIN

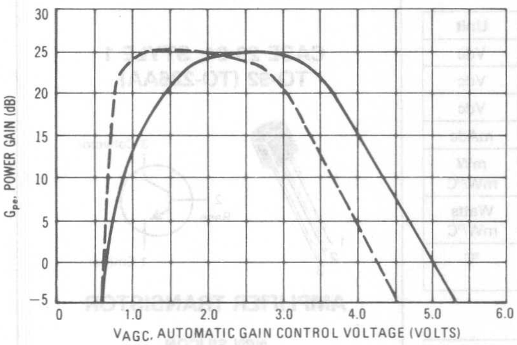


FIGURE 2 — NOISE FIGURE

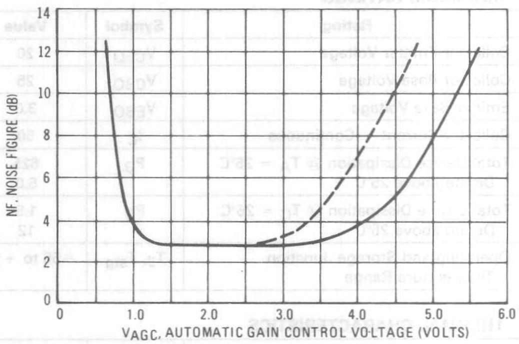


FIGURE 3 — 200 MHz FUNCTIONAL TEST CIRCUIT (NEUTRALIZED)

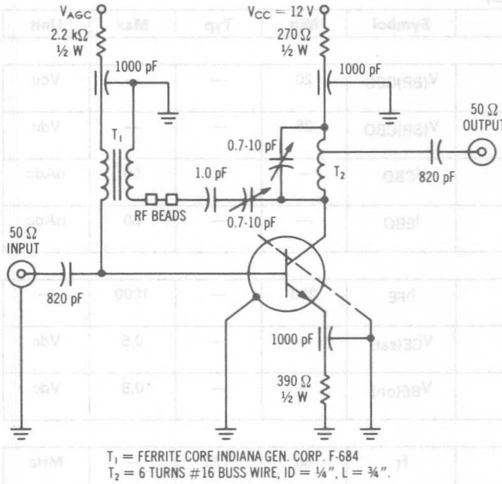
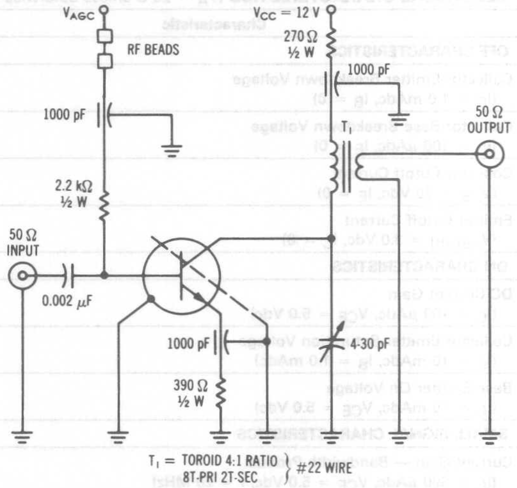


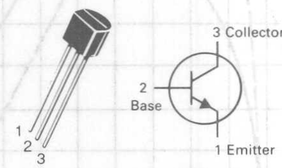
FIGURE 4 — 45 MHz FUNCTIONAL TEST CIRCUIT (UNNEUTRALIZED)



2

MPS6571

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MPSA18 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	20	Vdc
Collector-Base Voltage	V_{CBO}	25	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	50	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

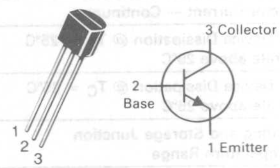
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	20	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	25	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$)	I_{CBO}	—	—	50	nAdc
Emitter Cutoff Current ($V_{EB(off)} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 100\ \mu$Adc, $V_{CE} = 5.0$ Vdc)	h_{FE}	250	—	1000	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	—	0.5	Vdc
Base-Emitter On Voltage ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc)	$V_{BE(on)}$	—	—	0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 500\ \mu$Adc, $V_{CE} = 5.0$ Vdc, f = 20 MHz)	f_T	50	175	—	MHz
Output Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	—	4.5	pF
Noise Figure ($I_C = 100\ \mu$Adc, $V_{CE} = 5.0$ Vdc, $R_S = 10$ kohms, f = 100 Hz)	NF	—	1.2	—	dB

MPS6576

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AUDIO TRANSISTOR

NPN SILICON

Refer to MPS3903 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	45	Vdc
Collector-Base Voltage	V_{CBO}	45	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	100	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	200	°C/mW

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(2) (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	45	—	Vdc
Collector Cutoff Current (V_{CB} = 45 Vdc, I_E = 0)	I_{CBO}	—	100	nAdc
Emitter Cutoff Current (V_{EB} = 4.0 Vdc, I_C = 0)	I_{EBO}	—	100	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}	100	300	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter On Voltage(2) (I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	$V_{BE(on)}$	—	0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product(2) (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 100 kHz)	f_T	100	350	MHz
Output Capacitance (V_{CB} = 12 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	12	pF

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

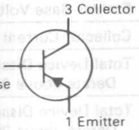
MPS6602/6652		40	
Collector-Base Voltage MPS6601/6651 MPS6602/6652	V_{CBO}	 25 30	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	1000	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

MPS6602

PNP

MPS6651

MPS6652



CASE 29-04, STYLE 1
TO-92 (TO-226AA)

AMPLIFIER TRANSISTOR

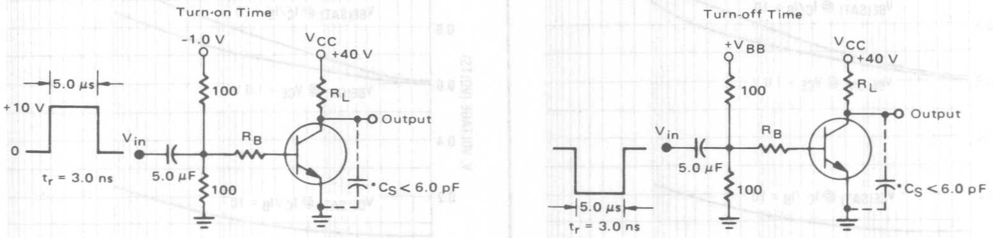
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	200	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

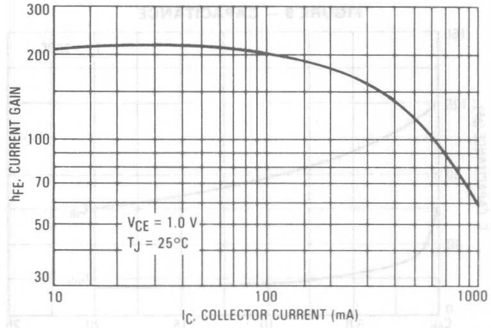
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	 MPS6601/6651 MPS6602/6652	$V_{(BR)CEO}$	 25 40	 — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	 MPS6601/6651 MPS6602/6652	$V_{(BR)CBO}$	 25 40	 — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 25$ Vdc, $I_B = 0$) ($V_{CE} = 30$ Vdc, $I_B = 0$)	 MPS6601/6651 MPS6602/6652	I_{CEO}	 — —	 0.1 0.1	μAdc
Collector Cutoff Current ($V_{CB} = 25$ Vdc, $I_E = 0$) ($V_{CB} = 30$ Vdc, $I_E = 0$)	 MPS6601/6651 MPS6602/6652	I_{CBO}	 — —	 0.1 0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 500$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1000$ mAdc, $V_{CE} = 1.0$ Vdc)		h_{FE}	 50 50 30	 — — —	—
Collector-Emitter Saturation Voltage ($I_C = 1000$ mAdc, $I_B = 100$ mAdc)		$V_{CE(sat)}$	—	0.6	Vdc
Base-Emitter On Voltage ($I_C = 500$ mAdc, $V_{CE} = 1.0$ Vdc)		$V_{BE(on)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 30 MHz)		f_T	100	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)		C_{obo}	—	30	pF
SWITCHING CHARACTERISTICS					
Delay Time	($V_{CC} = 40$ Vdc, $I_C = 500$ mAdc, $I_{B1} = 50$ mAdc, $t_p \geq 300$ ns Duty Cycle)	t_d	—	25	ns
Rise Time		t_r	—	30	ns
Storage Time		t_s	—	250	ns
Fall Time		t_f	—	50	ns



*Total Shunt Capacitance of Test Jig and Connectors
For PNP Test Circuits, Reverse All Voltage Polarities

NPN

FIGURE 2 — MPS6601/6602 DC CURRENT GAIN



PNP

FIGURE 3 — MPS6651/6652 DC CURRENT GAIN

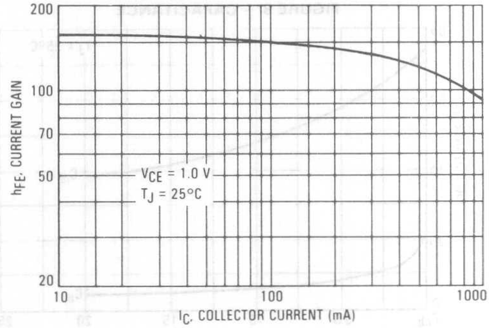


FIGURE 4 — CURRENT GAIN BANDWIDTH PRODUCT

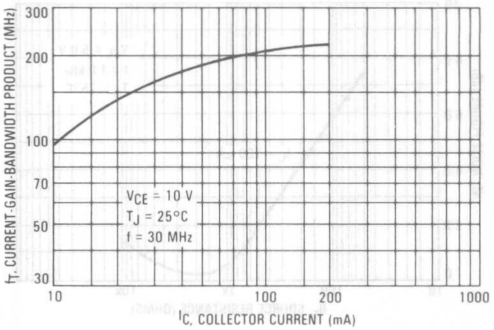


FIGURE 5 — CURRENT GAIN BANDWIDTH PRODUCT

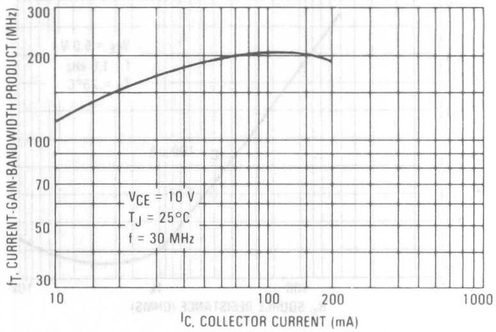


FIGURE 6 — ON VOLTAGES

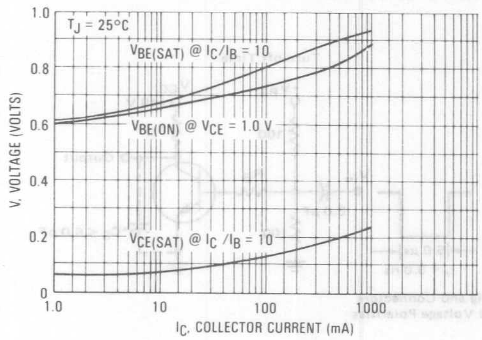
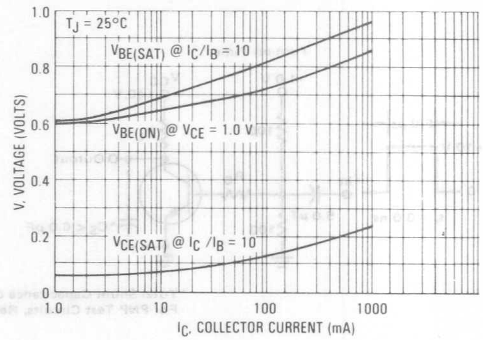
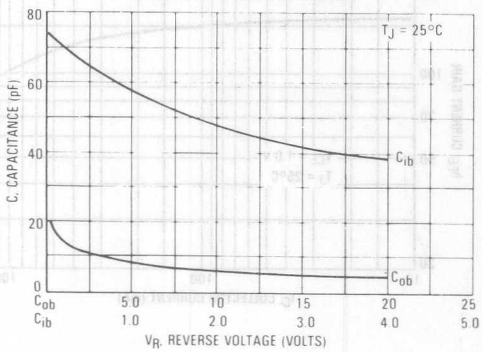


FIGURE 7 — ON VOLTAGES



NPN

FIGURE 8 — CAPACITANCE



PNP

FIGURE 9 — CAPACITANCE

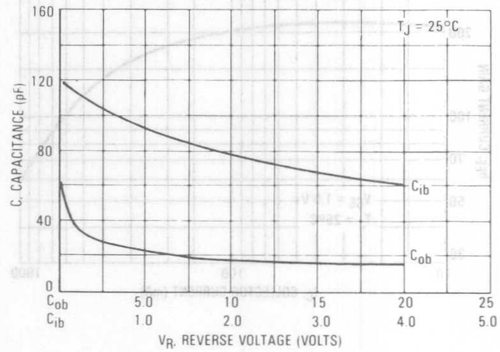


FIGURE 10 — MPS6601/6602 NOISE FIGURE

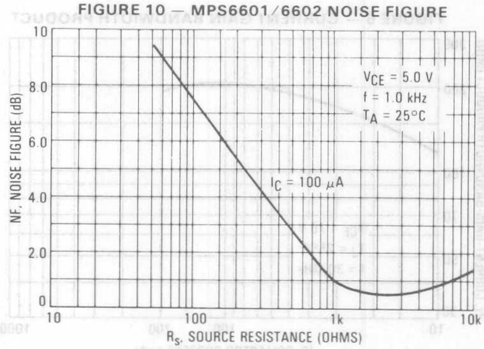


FIGURE 11 — MPS6651/6652 NOISE FIGURE

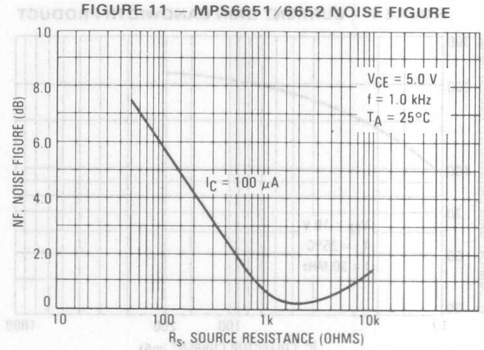


FIGURE 12 — MPS6601/6602 SWITCHING TIMES

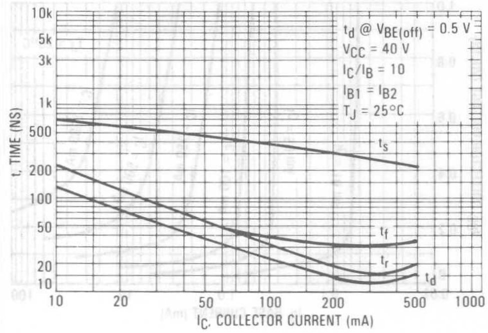
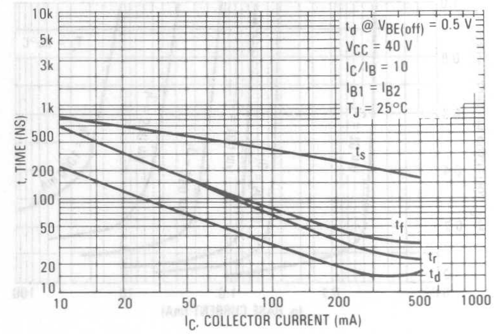
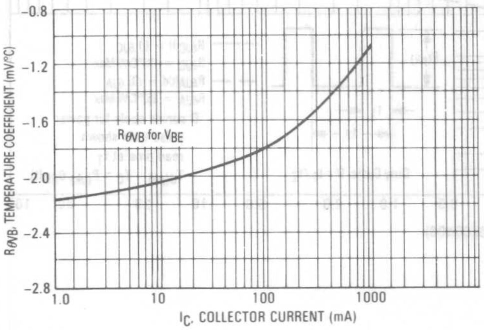


FIGURE 13 — MPS6651/6652 SWITCHING TIMES



NPN

FIGURE 14 — BASE-EMITTER TEMPERATURE COEFFICIENT



PNP

FIGURE 15 — BASE-EMITTER TEMPERATURE COEFFICIENT

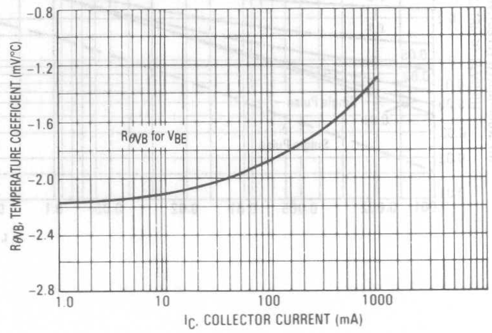


FIGURE 16 — SAFE OPERATING AREA

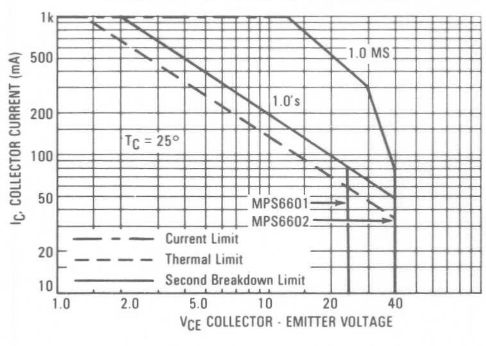
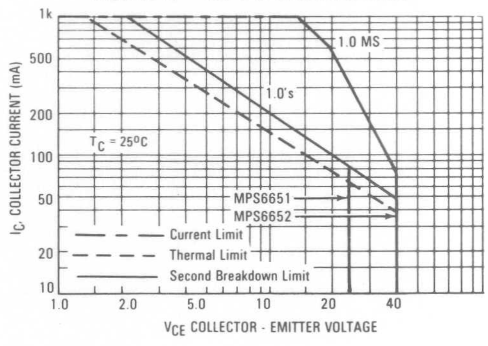
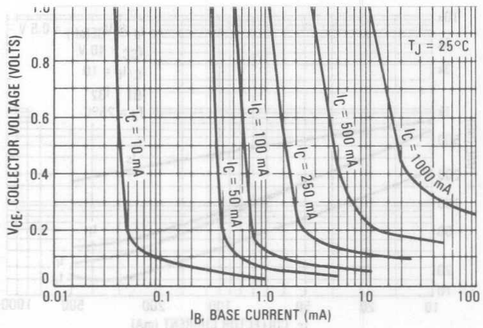


FIGURE 17 — SAFE OPERATING AREA





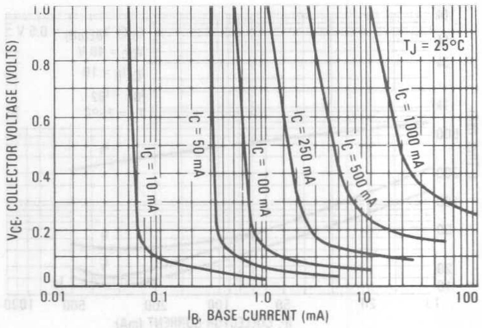
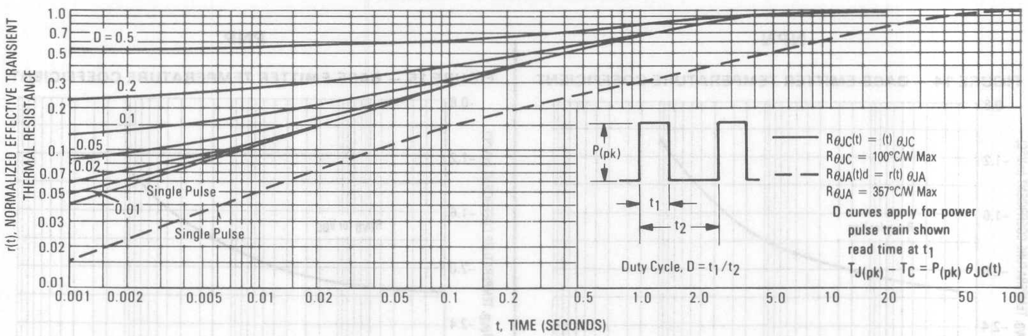


FIGURE 20 — THERMAL RESPONSE

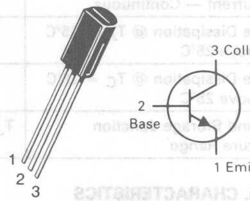


Collector-Emitter Voltage MPS6714 MPS6715	V_{CEO}	 30 40	Vdc
Collector-Base Voltage MPS6714 MPS6715	V_{CBO}	 40 50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	1.0	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 20	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

MPS6714
MPS6715

2

CASE 29-03, STYLE 1
TO-92 (TO-226 AE)



AMPLIFIER TRANSISTOR

NPN SILICON

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

Refer to MPSW01 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	 MPS6714 MPS6715	$V_{(BR)CEO}$	 30 40	 —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	 MPS6714 MPS6715	$V_{(BR)CBO}$	 40 50	 —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 40$ Vdc, $I_E = 0$) ($V_{CB} = 50$ Vdc, $I_E = 0$)	 MPS6714 MPS6715	I_{CBO}	 — —	 0.1 0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 5.0$ Vdc, $I_C = 0$)		I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1000$ mAdc, $V_{CE} = 1.0$ Vdc)		h_{FE}	 60 50	 — 250	—
Collector-Emitter Saturation Voltage ($I_C = 1000$ mAdc, $I_B = 100$ mAdc)		$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter On Voltage ($I_C = 1000$ mAdc, $V_{CE} = 1.0$ Vdc)		$V_{BE(on)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{cb}	—	30	pF
Small-Signal Current Gain ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)		h_{fe}	2.5	25	—

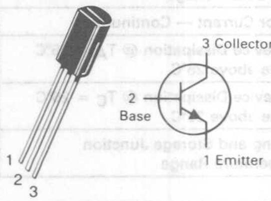
(1) Pulse Test: Pulse Width ≤ 30 μs, Duty Cycle ≤ 2.0%.

MAXIMUM RATINGS

Rating	Symbol	MPS6516	MPS6517	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	Vdc
Collector-Base Voltage	V_{CBO}	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 8.0		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 20		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

MPS6716
MPS6717

CASE 29-03, STYLE 1
TO-92 (TO-226 AE)



AMPLIFIER TRANSISTOR

NPN SILICON

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

Refer to MPSW05 for graphs.

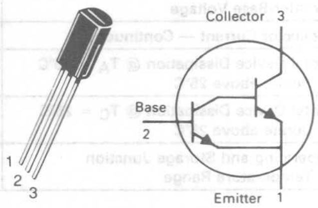
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	 MPS6716 MPS6717	$V_{(BR)CEO}$	 60 80	 — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	 MPS6716 MPS6717	$V_{(BR)CBO}$	 60 80	 — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 40$ Vdc, $I_E = 0$) ($V_{CB} = 60$ Vdc, $I_E = 0$)	 MPS6716 MPS6717	I_{CBO}	 — —	 0.1 0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 5.0$ Vdc, $I_C = 0$)		I_{EBO}	—	10	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 250$ mAdc, $V_{CE} = 1.0$ Vdc)		h_{FE}	 80 50	 — 250	—
Collector-Emitter Saturation Voltage ($I_C = 250$ mAdc, $I_B = 10$ mAdc)		$V_{CE(sat)}$		0.5	Vdc
Base-Emitter On Voltage ($I_C = 250$ mAdc, $V_{CE} = 1.0$ Vdc)		$V_{BE(on)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{cb}	—	30	pF
Small-Signal Current Gain ($I_C = 200$ mAdc, $V_{CE} = 5.0$ Vdc, f = 20 MHz)		h_{fe}	2.5	25	—

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MPS6724
MPS6725

CASE 29-03, STYLE 1
(TO-226 AE)



DARLINGTON TRANSISTOR

NPN SILICON

2

MAXIMUM RATINGS

Rating	Symbol	MPS6724	MPS6725	Unit
Collector-Emitter Voltage	V_{CES}	40	50	Vdc
Collector-Base Voltage	V_{CBO}	50	60	Vdc
Emitter-Base Voltage	V_{EBO}	12		Vdc
Collector Current — Continuous	I_C	1000		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 8.0		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 20		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

Refer to 2N6426 for graphs.

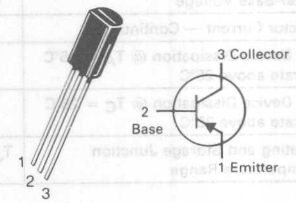
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	 MPS6724 MPS6725	$V_{(BR)CES}$	 40 50	 — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 1.0$ μAdc, $I_E = 0$)	 MPS6724 MPS6725	$V_{(BR)CBO}$	 50 60	 — —	 Vdc Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	12		Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$) ($V_{CB} = 40$ Vdc, $I_E = 0$)	 MPS6724 MPS6725	I_{CBO}	 — —	 100 100	nAdc
Emitter Cutoff Current ($V_{EB} = 10$ Vdc, $I_C = 0$)		I_{EBO}	—	100	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 200$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 1000$ mAdc, $V_{CE} = 5.0$ Vdc)		h_{FE}	 25,000 4,000	 — 40,000	—
Collector-Emitter Saturation Voltage ($I_C = 1000$ mAdc, $I_B = 2.0$ mAdc)		$V_{CE(sat)}$		1.5	Vdc
Base-Emitter On Voltage ($I_C = 1000$ mAdc, $V_{CE} = 5.0$ Vdc)		$V_{BE(on)}$	—	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 200$ mAdc, $V_{CE} = 5.0$ Vdc, f = 100 MHz)		f_T	100	1000	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{cb}	—	10	pF

2

MPS6726
MPS6727

CASE 29-03, STYLE 1
TO-92 (TO-226 AE)



AMPLIFIER TRANSISTOR

PNP SILICON

Refer to MPSW51 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage MPS6726 MPS6727	V_{CEO}	 30 40	Vdc
Collector-Base Voltage MPS6726 MPS6727	V_{CBO}	 40 50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	1.0	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 20	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

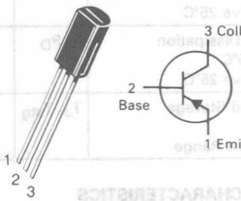
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 10$ mAdc, $I_B = 0$)	 MPS6726 MPS6727	$V_{(BR)CEO}$	 30 40	 —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	 MPS6726 MPS6727	$V_{(BR)CBO}$	 40 50	 —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 40$ Vdc, $I_E = 0$) ($V_{CB} = 50$ Vdc, $I_E = 0$)	 MPS6726 MPS6727	I_{CBO}	 —	 0.1 0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 5.0$ Vdc, $I_C = 0$)		I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1000$ mAdc, $V_{CE} = 1.0$ Vdc)		h_{FE}	 60 50	 — 250	—
Collector-Emitter Saturation Voltage ($I_C = 1000$ mAdc, $I_B = 100$ mAdc)		$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter On Voltage ($I_C = 1000$ mAdc, $V_{CE} = 1.0$ Vdc)		$V_{BE(on)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{cb}	—	30	pF
Small-Signal Current Gain ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)		h_{fe}	2.5	25	—

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MPS6728
MPS6729

CASE 29-03, STYLE 1
TO-92 (TO-226 AE)



AMPLIFIER TRANSISTOR

PNP SILICON

Refer to MPSW55 for graphs.

MAXIMUM RATINGS

Rating	Symbol	MPS6728	MPS6729	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	Vdc
Collector-Base Voltage	V_{CBO}	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 8.0		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 20		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

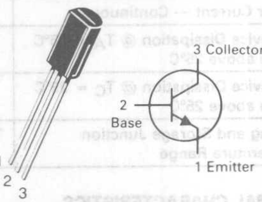
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	MPS6728 MPS6729	$V_{(BR)CEO}$	60 80	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	MPS6728 MPS6729	$V_{(BR)CBO}$	60 80	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{EB} = 5.0$ Vdc, $I_C = 0$)		I_{EBO}	—	10	μAdc
Emitter Cutoff Current ($V_{CB} = 40$ Vdc, $I_E = 0$) ($V_{CB} = 60$ Vdc, $I_E = 0$)	MPS6728 MPS6729	I_{CBO}	— —	0.1 0.1	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 250$ mAdc, $V_{CE} = 1.0$ Vdc)		h_{FE}	80 50	 250	 —
Collector-Emitter Saturation Voltage ($I_C = 250$ mAdc, $I_B = 10$ mAdc)		$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter On Voltage ($I_C = 250$ mAdc, $V_{CE} = 1.0$ Vdc)		$V_{BE(on)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{cb}	—	30	pF
Small-Signal Current Gain ($I_C = 200$ mAdc, $V_{CE} = 5.0$ Vdc, f = 20 MHz)		h_{fe}	2.5	25	—

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MPS6733
MPS6734
MPS6735

CASE 29-03, STYLE 1
TO-92 (TO-226 AE)



HIGH VOLTAGE TRANSISTOR

NPN SILICON

Refer to MPSW42 for graphs.

MAXIMUM RATINGS

Rating	Symbol	MPS6735	MPS6734	MPS6733	Unit
Collector-Emitter Voltage	V_{CEO}	300	250	200	Vdc
Collector-Base Voltage	V_{CBO}	300	250	200	Vdc
Emitter-Base Voltage	V_{EBO}		6.0		Vdc
Collector Current — Continuous	I_C		300		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D		1.0 8.0		Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D		2.5 20		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

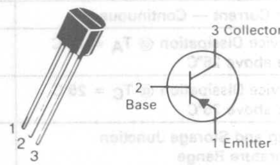
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	MPS6735 MPS6734 MPS6733	$V_{(BR)CEO}$	300 250 200	— — —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	MPS6735 MPS6734 MPS6733	$V_{(BR)CBO}$	300 250 200	— — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current (V_{CB} = 260 Vdc, I_E = 0) (V_{CB} = 200 Vdc, I_E = 0) (V_{CB} = 160 Vdc, I_E = 0)	MPS6735 MPS6734 MPS6733	I_{CBO}	— — —	0.1 0.1 0.1	μAdc
Emitter Cutoff Current (V_{EB} = 6.0 Vdc, I_C = 0)		I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc)		h_{FE}	25 40	— 200	
Collector-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)		$V_{CE(sat)}$	—	2.0	Vdc
Base-Emitter On Voltage (I_C = 20 mAdc, V_{CE} = 10 Vdc)		$V_{BE(on)}$	—	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 20 MHz)		f_T	50	200	MHz
Collector-Base Capacitance (V_{CB} = 20 Vdc, I_E = 0, f = 1.0 MHz)		C_{cb}	—	3.0	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MPS8093

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

Refer to 2N4402 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 60°C$	P_D	450	mW
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

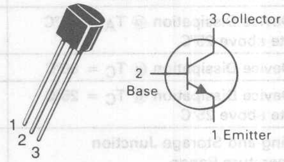
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 10$ mAdc)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu$Adc)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 20$ V)	I_{CBO}	—	100	nAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ V)	I_{EBO}	—	100	nAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 50$ mAdc, $V_{CE} = 2.0$ Vdc)	h_{FE}	100	300	—
Collector-Emitter Saturation Voltage ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)	$V_{CE(sat)}$	—	0.25	Vdc
Base-Emitter On Voltage ($I_C = 50$ mAdc, $V_{CE} = 2.0$ V)	$V_{BE(on)}$	0.6	1.0	Vdc

MPS8097

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MPSA18 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

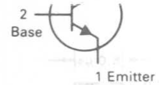
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

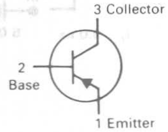
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	Vdc
Collector Cutoff Current (V_{CB} = 40 Vdc, I_E = 0) (V_{CB} = 60 Vdc, I_E = 0)	I_{CBO}	 — —	 30 10	 nAdc μAdc
Emitter Cutoff Current (V_{BE} = 6.0 Vdc, I_C = 0)	I_{EBO}	—	20	nAdc
ON CHARACTERISTICS(2)				
DC Current Gain (I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	h_{FE}	250	700	—
Base-Emitter On Voltage (I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	$V_{BE(on)}$	0.45	0.65	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	1.0	4.0	pF
Emitter-Base Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{eb}	—	10	pF
Small-Signal Current Gain (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{fe}	250	800	—
Noise Figure (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = kΩ, f = 10 Hz to 15.7 kHz)	NF	—	2.0	dB
Equivalent Short Circuit Noise Voltage (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 kΩ, f = 100 Hz, Bw = 1.0 Hz)	e_n	—	32	nV/$\sqrt{Hz}$

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.
(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

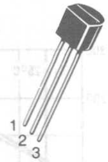
MPS8098
MPS8099



PNP
MPS8598
MPS8599



CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

Rating	Symbol	MPS8098 MPS8598	MPS8099 MPS8599	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	Vdc
Collector-Base Voltage	V_{CBO}	60	80	Vdc
		MPS8098 MPS8099	MPS8598 MPS8599	
Emitter-Base Voltage	V_{EBO}	6.0	5.0	Vdc
Collector Current — Continuous	I_C	500		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12.0		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

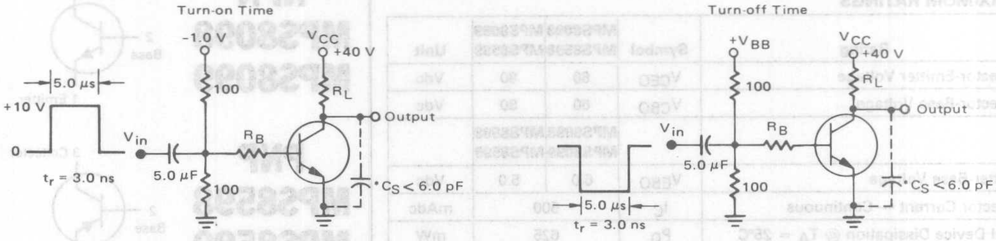
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	 MPS8098, MPS8598 MPS8099, MPS8599	$V_{(BR)CEO}$	 60 80	 — —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	 MPS8098, MPS8598 MPS8099, MPS8599	$V_{(BR)CBO}$	 60 80	 — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	 MPS8098, MPS8099 MPS8598, MPS8599	$V_{(BR)EBO}$	 6.0 5.0	 — —	Vdc
Collector Cutoff Current (V_{CE} = 60 Vdc, I_B = 0)		I_{CEO}	—	0.1	μAdc
Collector Cutoff Current (V_{CB} = 60 Vdc, I_E = 0) (V_{CB} = 80 Vdc, I_E = 0)	 MPS8098, MPS8598 MPS8099, MPS8599	I_{CBO}	 — —	 0.1 0.1	μAdc
Emitter Cutoff Current (V_{EB} = 6.0 Vdc, I_C = 0) (V_{EB} = 4.0 Vdc, I_C = 0)	 MPS8098, MPS8099 MPS8598, MPS8599	I_{EBO}	 — —	 0.1 0.1	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc) (I_C = 10 mAdc, V_{CE} = 5.0 Vdc) 0(I_C = 100 mAdc, V_{CE} = 5.0 Vdc)		h_{FE}	100 100 75	300 — —	—
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 5.0 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc)		$V_{CE(sat)}$	— —	0.4 0.3	Vdc
Base-Emitter On Voltage (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc) (I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	 MPS8098, MPS8598 MPS8099, MPS8599	$V_{BE(on)}$	 0.5 0.6	 0.7 0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)		f_T	150	—	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	 MPS8098, MPS8099 MPS8598, MPS8599	C_{obo}	 — —	 6.0 8.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	 MPS8098, MPS8099 MPS8598, MPS8599	C_{ibo}	 — —	 25 30	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 2.0%.

2

FIGURE 1 – SWITCHING TIME TEST CIRCUITS



*Total Shunt Capacitance of Test Jig and Connectors
For PNP Test Circuits, Reverse All Voltage Polarities

FIGURE 2 – CURRENT-GAIN – BANDWIDTH PRODUCT

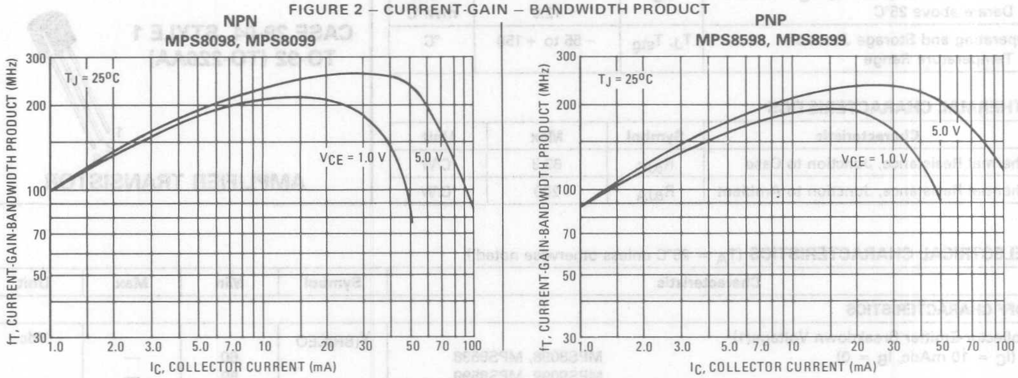


FIGURE 3 – CAPACITANCE

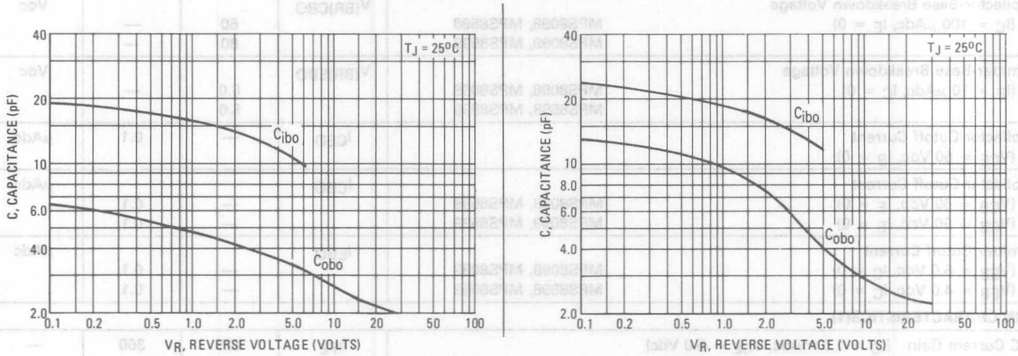


FIGURE 4 – SWITCHING TIMES

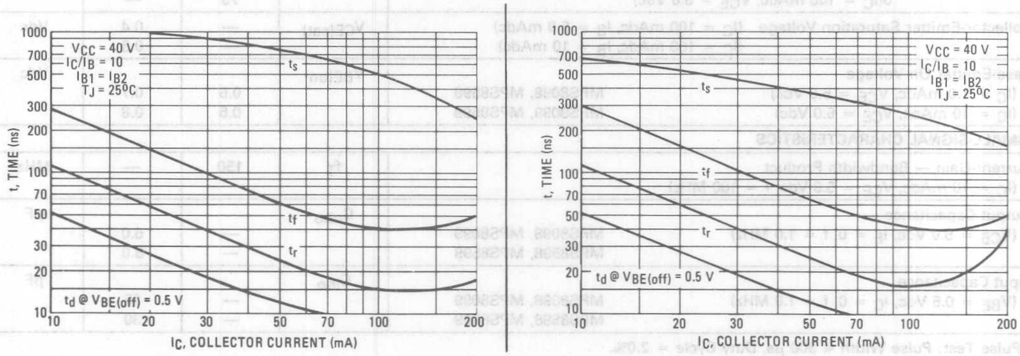


FIGURE 5 — THERMAL RESPONSE

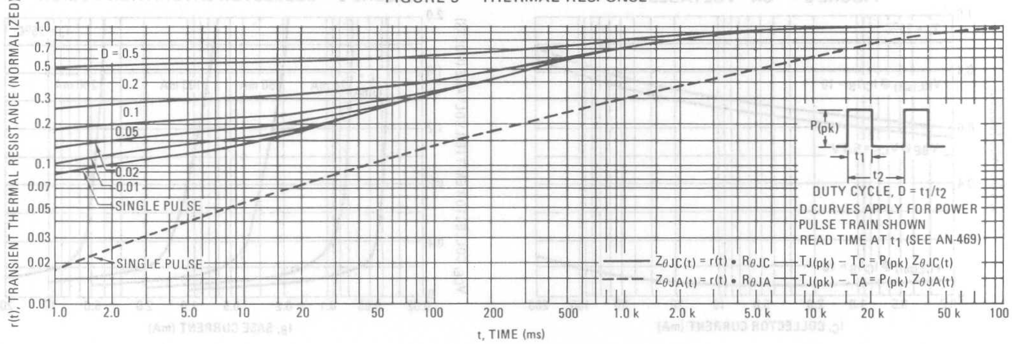


FIGURE 6—ACTIVE REGION, SAFE OPERATING AREA
MPS 8098, MPS 8099

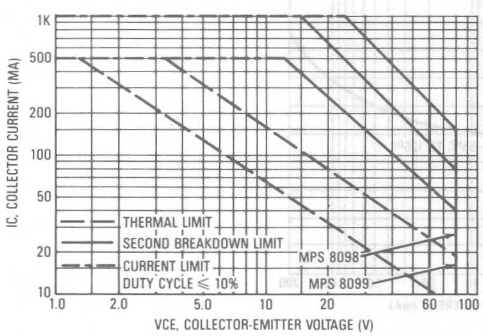
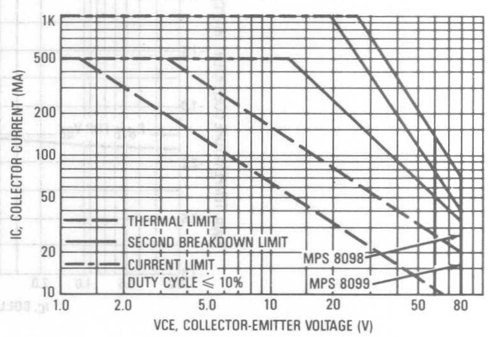


FIGURE 6—ACTIVE REGION, SAFE OPERATING AREA
MPS 8598, MPS 8599



MPS8098, MPS8099

FIGURE 7 — DC CURRENT GAIN

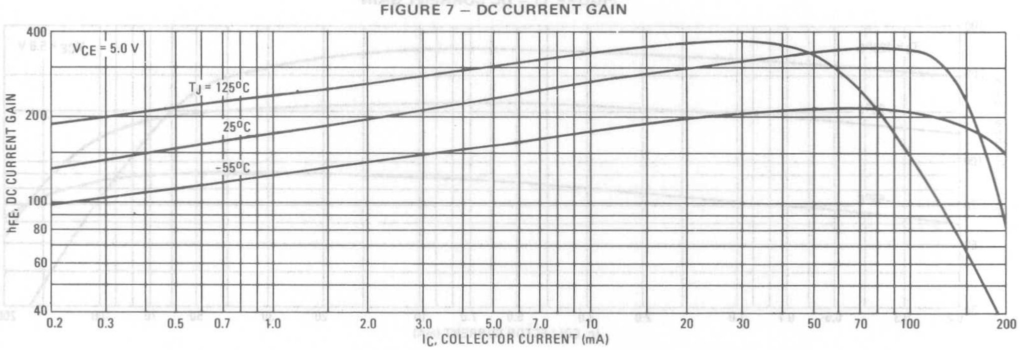


FIGURE 8 – "ON" VOLTAGES

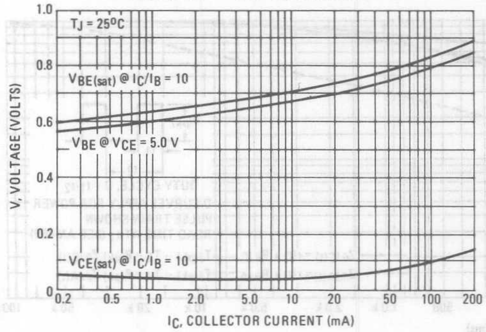


FIGURE 9 – COLLECTOR SATURATION REGION

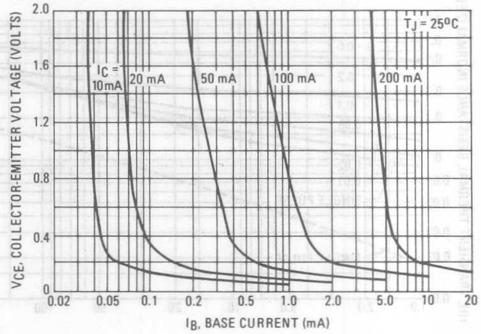
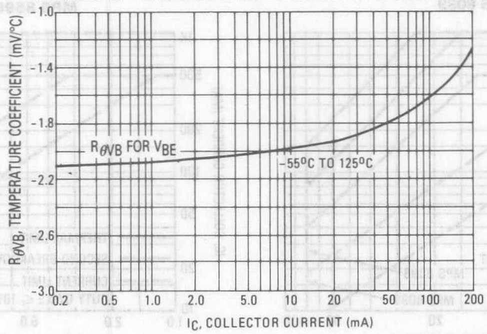


FIGURE 10 – BASE-EMITTER TEMPERATURE COEFFICIENT



MPS8598, MPS8599

FIGURE 11 – DC CURRENT GAIN

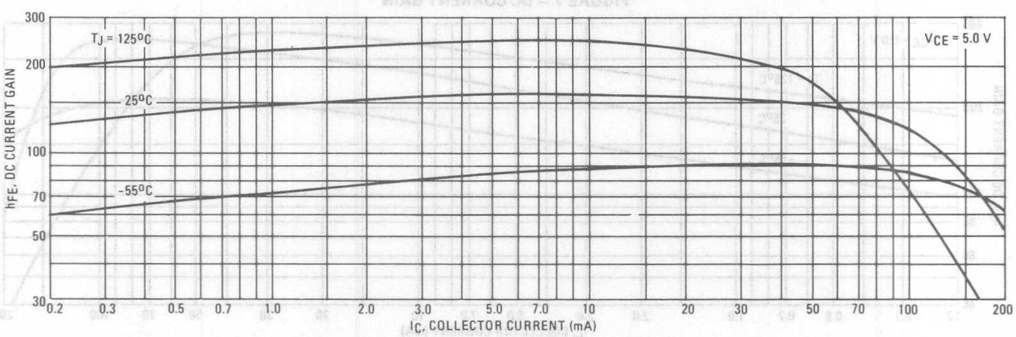


FIGURE 12 — "ON" VOLTAGES

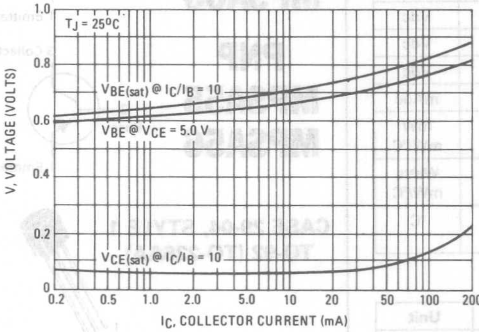


FIGURE 13 — COLLECTOR SATURATION REGION

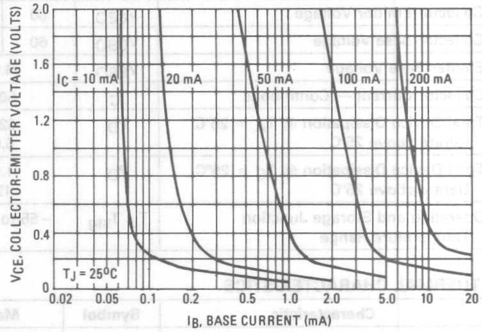
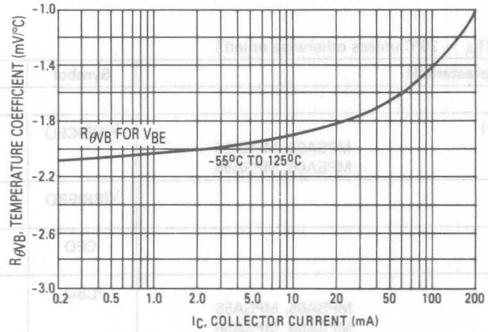


FIGURE 14 — BASE-EMITTER TEMPERATURE COEFFICIENT



2

MAXIMUM RATINGS

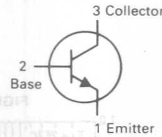
Rating	Symbol	MPSA05 MPSA55	MPSA06 MPSA56	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	Vdc
Collector-Base Voltage	V_{CBO}	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	4.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

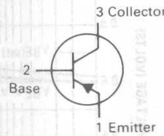
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	200	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

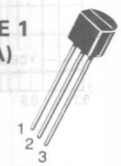
NPN
MPSA05
MPSA06



PNP
MPSA55
MPSA56



CASE 29-04, STYLE 1
TO-92 (TO-226AA)



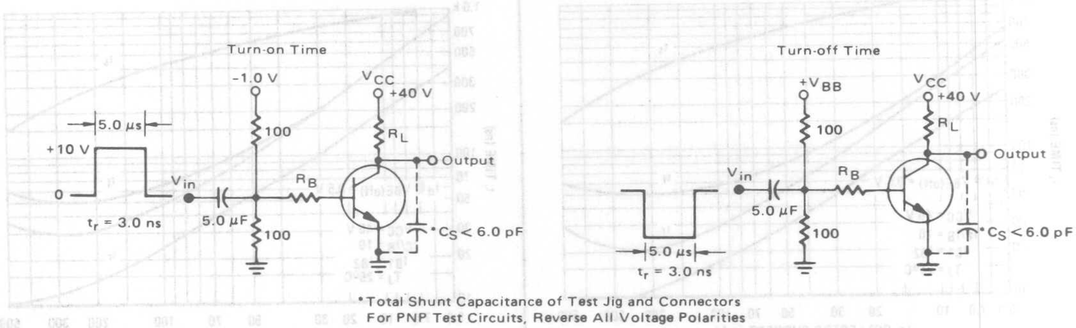
AMPLIFIER TRANSISTOR

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)	 MPSA05, MPSA55 MPSA06, MPSA56	$V_{(BR)CEO}$	 60 80	 — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current (V_{CE} = 60 Vdc, I_B = 0)		I_{CEO}	—	0.1	μAdc
Collector Cutoff Current (V_{CB} = 60 Vdc, I_E = 0) (V_{CB} = 80 Vdc, I_E = 0)	 MPSA05, MPSA55 MPSA06, MPSA56	I_{CBO}	 — —	 0.1 0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 10 mAdc, V_{CE} = 1.0 Vdc) (I_C = 100 mAdc, V_{CE} = 1.0 Vdc)		h_{FE}	 50 50	 — —	—
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 10 mAdc)		$V_{CE(sat)}$	—	0.25	Vdc
Base-Emitter On Voltage (I_C = 100 mAdc, V_{CE} = 1.0 Vdc)		$V_{BE(on)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 10 mA, V_{CE} = 2.0 V, f = 100 MHz) (I_C = 100 mAdc, V_{CE} = 1.0 Vdc, f = 100 MHz)	 MPSA05 MPSA06 MPSA55 MPSA56	f_T	 100 50	 — —	MHz

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

FIGURE 1 – SWITCHING TIME TEST CIRCUITS



*Total Shunt Capacitance of Test Jig and Connectors
For PNP Test Circuits, Reverse All Voltage Polarities

FIGURE 2 – CURRENT-GAIN–BANDWIDTH PRODUCT

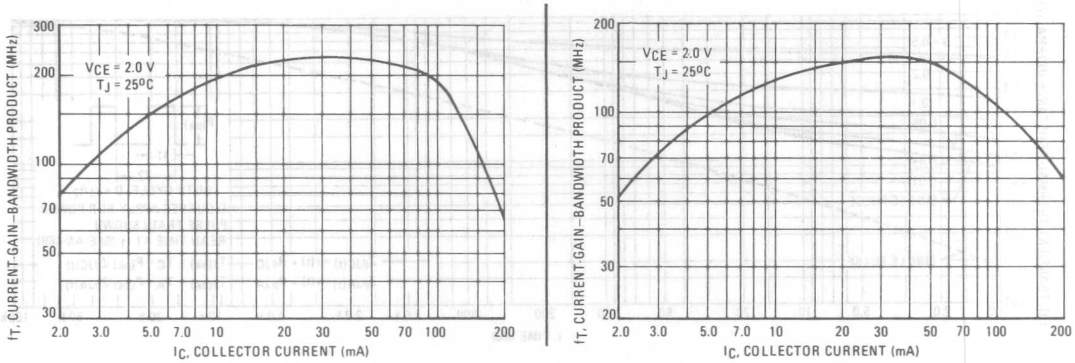


FIGURE 3 – CAPACITANCE

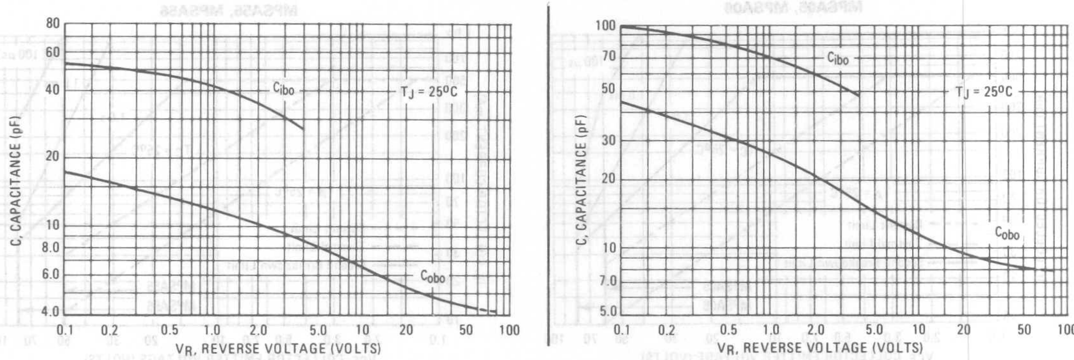


FIGURE 4 – SWITCHING TIME

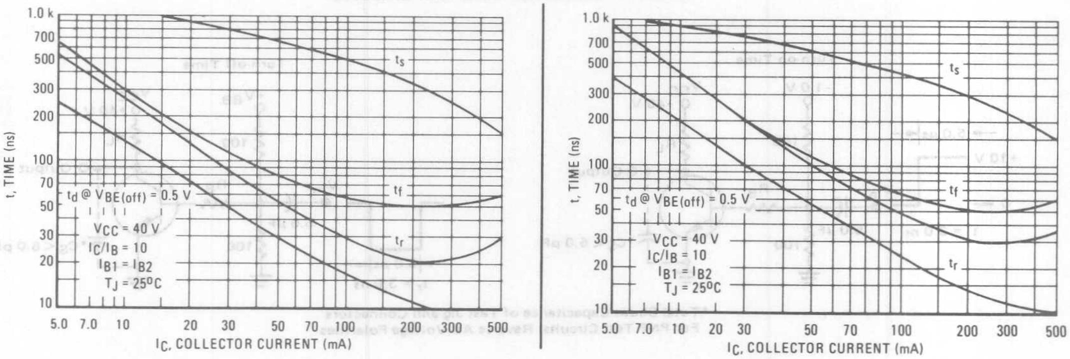


FIGURE 5 – THERMAL RESPONSE

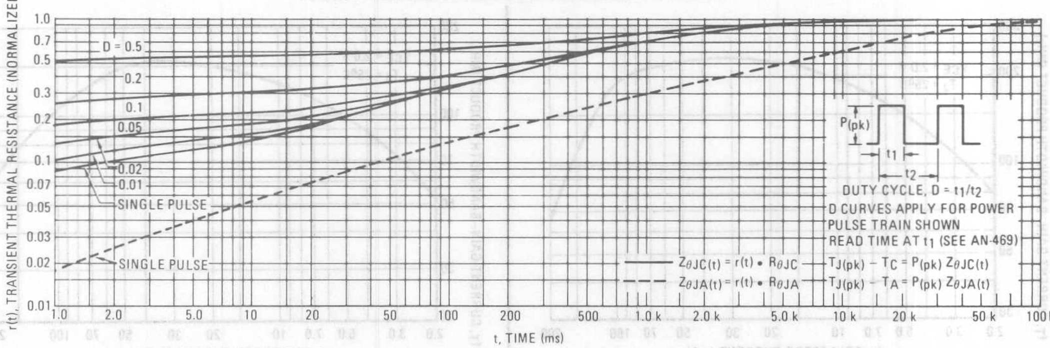
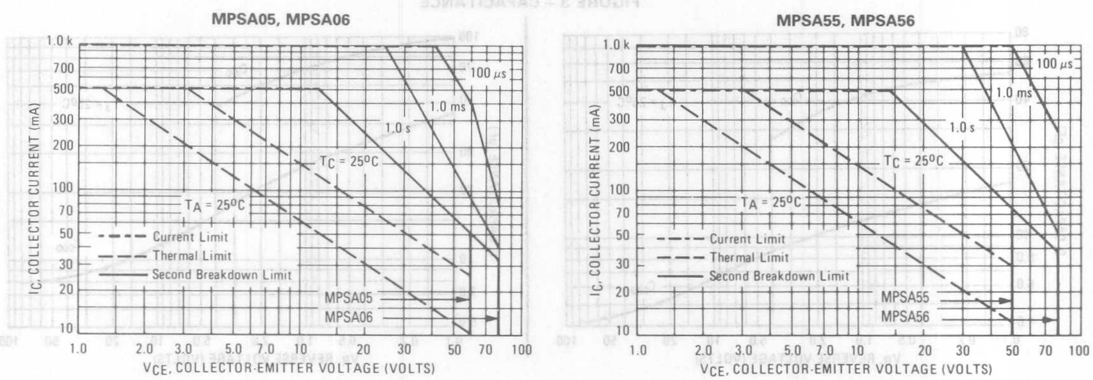


FIGURE 6 – ACTIVE – REGION SAFE OPERATING AREA



NPN
MPSA05, MPSA06

FIGURE 7 – DC CURRENT GAIN

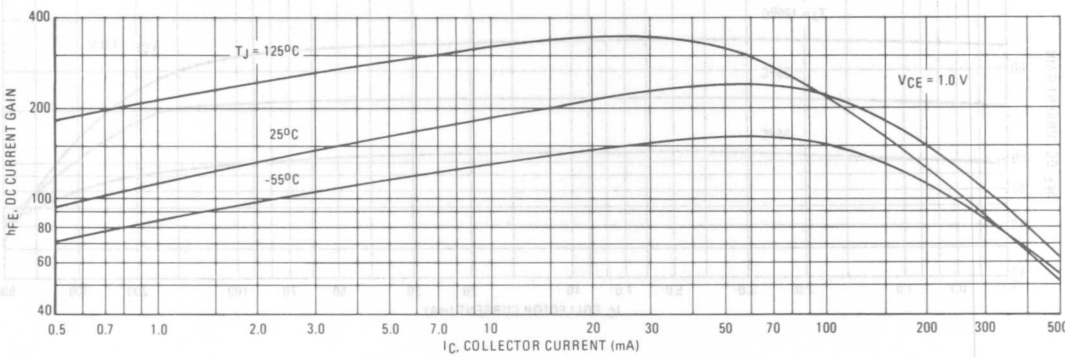


FIGURE 8 – "ON" VOLTAGES

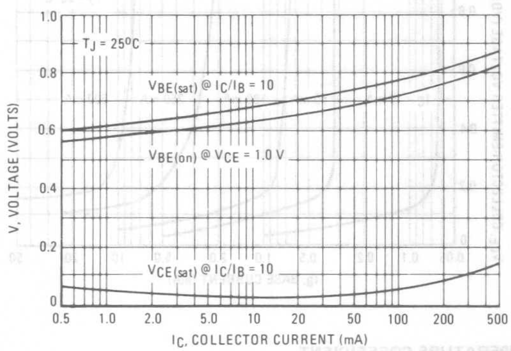


FIGURE 9 – COLLECTOR SATURATION REGION

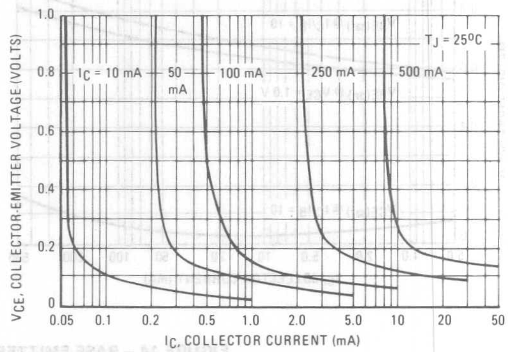
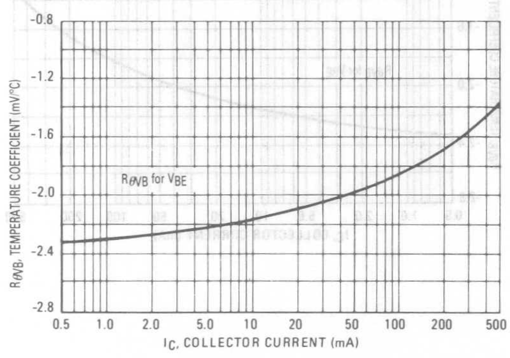


FIGURE 10 – BASE-EMITTER TEMPERATURE COEFFICIENT



2

PNP
MPSA55, MPSA56

FIGURE 11 — DC CURRENT GAIN

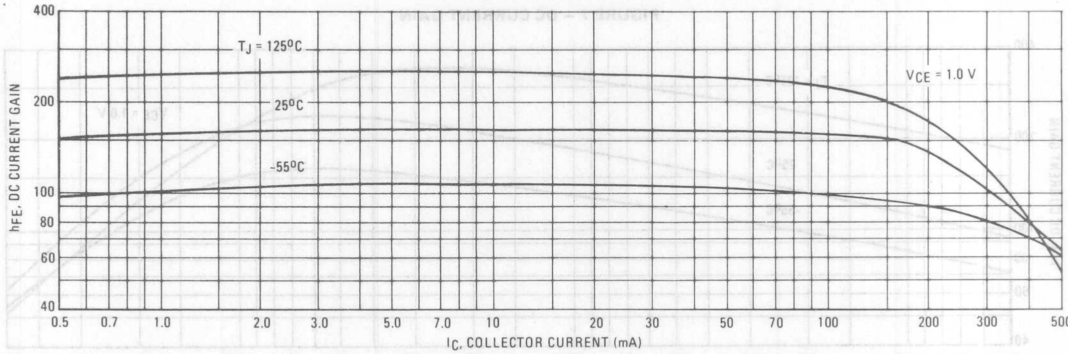


FIGURE 12 — "ON" VOLTAGES

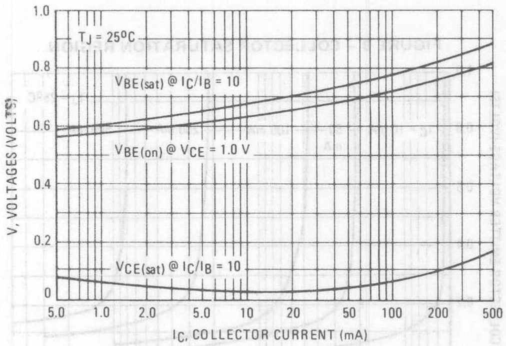


FIGURE 13 — COLLECTOR SATURATION REGION

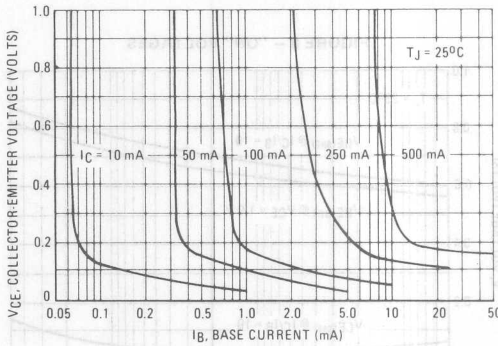
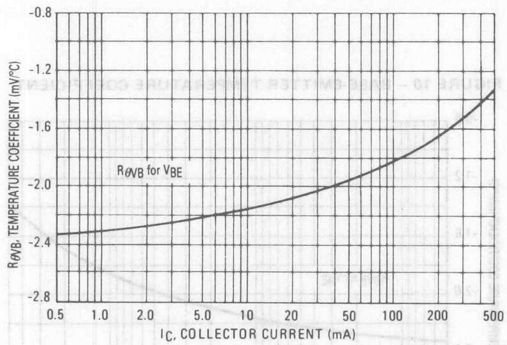
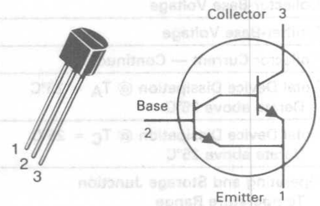


FIGURE 14 — BASE-EMITTER TEMPERATURE COEFFICIENT



MPSA12

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



DARLINGTON TRANSISTOR

NPN SILICON

Refer to 2N6426 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CES}	20	Vdc
Emitter-Base Voltage	V_{EBO}	10	Vdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

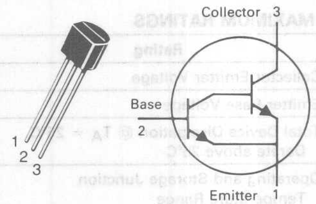
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 100\ \mu Adc$, $I_B = 0$)	$V_{(BR)CES}$	20	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_E = 0$)	I_{CBO}	—	—	100	nAdc
Collector Cutoff Current ($V_{CE} = 15$ Vdc, $V_{BE} = 0$)	I_{CES}	—	—	100	nAdc
Emitter Cutoff Current ($V_{EB} = 10$ Vdc, $I_C = 0$)	I_{EBO}	—	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc)	h_{FE}	20,000	—	—	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 0.01$ mAdc)	$V_{CE(sat)}$	—	—	1.0	Vdc
Base-Emitter On Voltage ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc)	V_{BE}	—	—	1.4	Vdc

MPSA13
MPSA14

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



DARLINGTON TRANSISTOR

NPN SILICON

Refer to 2N6426 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CES}	30	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	10	Vdc
Collector Current — Continuous	I_C	500	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	− 55 to + 150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

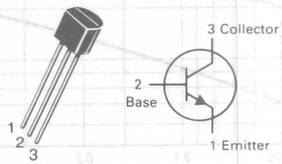
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 100\ \mu Adc$, $I_B = 0$)		$V_{(BR)CES}$	30	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)		I_{CBO}	—	100	nAdc
Emitter Cutoff Current ($V_{BE} = 10$ Vdc, $I_C = 0$)		I_{EBO}	—	100	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc)	MPSA13 MPSA14	h_{FE}	5000 10,000	— —	—
($I_C = 100$ mAdc, $V_{CE} = 5.0$ Vdc)	MPSA13 MPSA14		10,000 20,000	— —	
Collector-Emitter Saturation Voltage ($I_C = 100$ mAdc, $I_B = 0.1$ mAdc)		$V_{CE(sat)}$	—	1.5	Vdc
Base-Emitter On Voltage ($I_C = 100$ mAdc, $V_{CE} = 5.0$ Vdc)		V_{BE}	—	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc, f = 100 MHz)		f_T	125	—	MHz

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) $f_T = |h_{fe}| \cdot f_{test}$.

MPSA17

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



SWITCHING TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	MPS-A16	MPS-A17	Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Emitter-Base Voltage	V_{EBO}	12	15	Vdc
Collector Current — Continuous	I_C	100		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	40	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 0.1$ mAdc, $I_C = 0$)	MPS-A16 MPS-A17	$V_{(BR)EBO}$	12 15	— —	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)		I_{CBO}	—	100	nAdc
Emitter Cutoff Current ($V_{BE} = 10$ Vdc, $I_C = 0$)		I_{EBO}	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc)		h_{FE}	200	600	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)		$V_{CE(sat)}$	—	0.25	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	MPS-A16 MPS-A17	f_T	100 80	— —	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)		C_{obo}	—	4.0	pF

FIGURE 1 – DC CURRENT GAIN

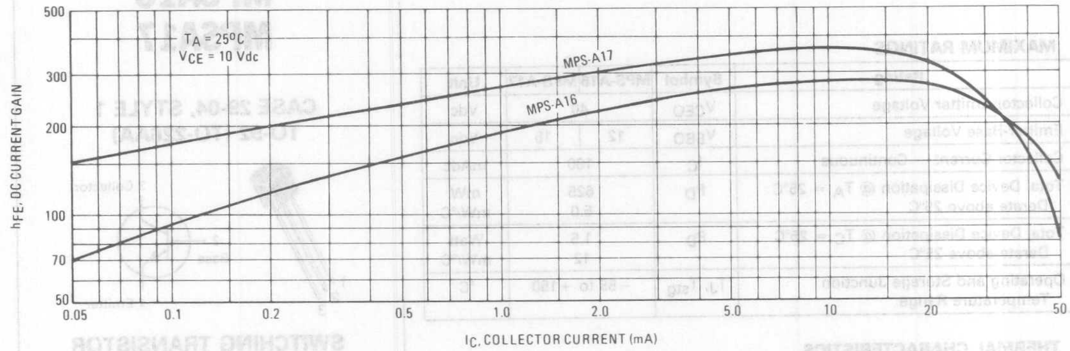


FIGURE 2 – SMALL SIGNAL CURRENT GAIN

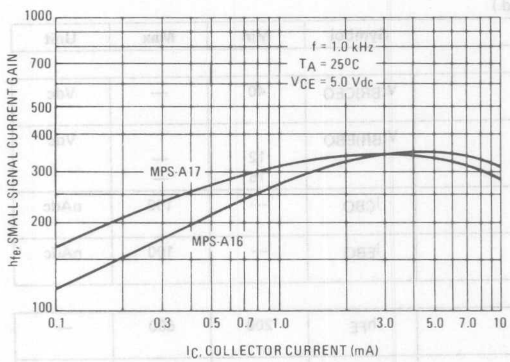


FIGURE 3 – SATURATION AND ON VOLTAGES

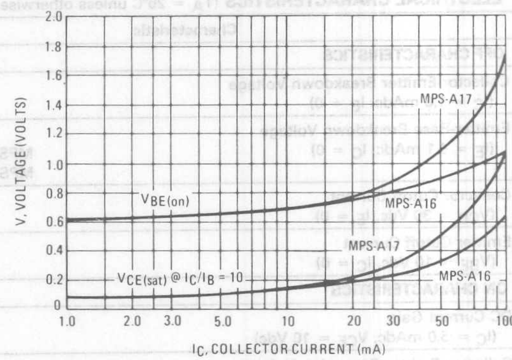


FIGURE 4 – CURRENT-GAIN–BANDWIDTH PRODUCT

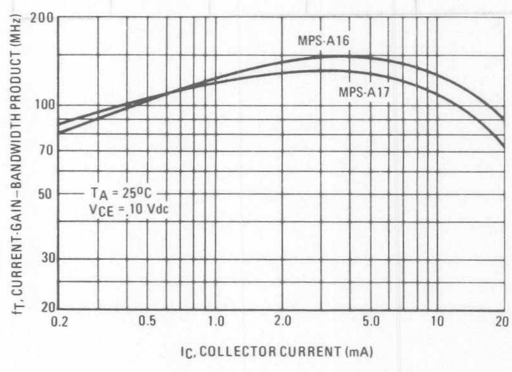
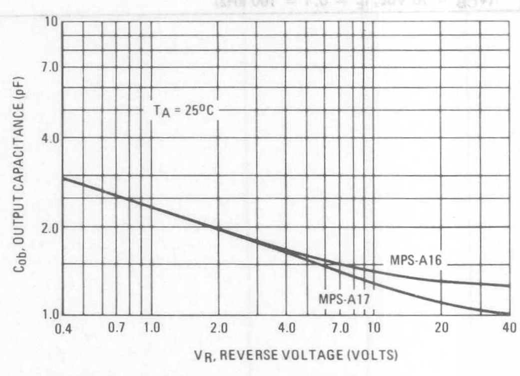
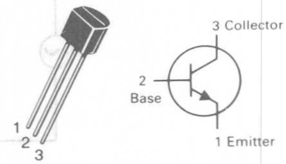


FIGURE 5 – OUTPUT CAPACITANCE



MPSA18

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



LOW NOISE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	45	Vdc
Collector-Base Voltage	V_{CBO}	45	Vdc
Emitter-Base Voltage	V_{EBO}	6.5	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

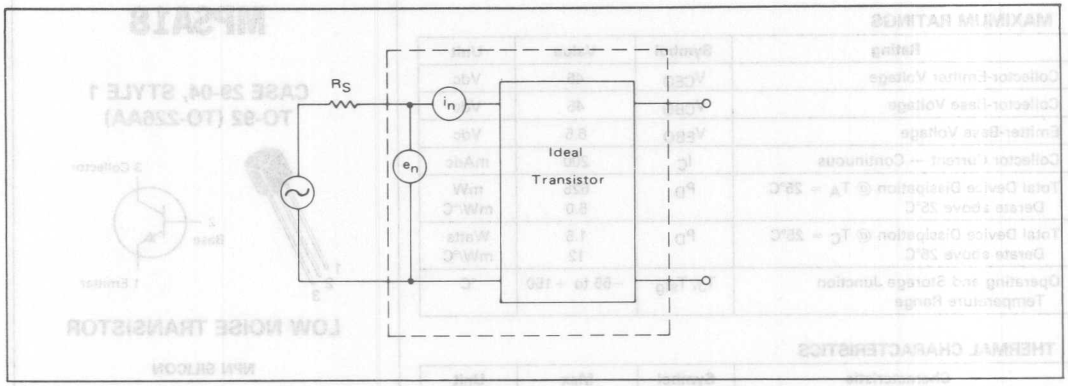
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	45	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	45	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	6.5	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	1.0	50	nAdc
ON CHARACTERISTICS(2)					
DC Current Gain ($I_C = 10$ μAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 100$ μAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc)	h_{FE}	 400 500 500 500	 580 850 1100 1150	 — — — 1500	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 0.5$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)	$V_{CE(sat)}$	 — —	 — 0.08	 0.2 0.3	Vdc
Base-Emitter On Voltage ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc)	$V_{BE(on)}$	—	0.6	0.7	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 100 MHz)	f_T	100	160	—	MHz
Collector-Base Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{cb}	—	1.7	3.0	pF
Emitter-Base Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)	C_{eb}	—	5.6	6.5	pF
Noise Figure ($I_C = 100$ μAdc, $V_{CE} = 5.0$ Vdc, $R_S = 10$ kΩ, f = 10 Hz to 15.7 kHz) ($I_C = 100$ μAdc, $V_{CE} = 5.0$ Vdc, $R_S = 1.0$ kΩ, f = 100 Hz)	NF	 — —	 0.5 4.0	 1.5 —	dB
Equivalent Short Circuit Noise Voltage ($I_C = 100$ μAdc, $V_{CE} = 5.0$ Vdc, $R_S = 1.0$ kΩ, f = 100 Hz)	V_T	—	6.5	—	$nV/\sqrt{Hz}$

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.
(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 – TRANSISTOR NOISE MODEL



NOISE CHARACTERISTICS

(V_{CE} = 5.0 Vdc, T_A = 25°C)

NOISE VOLTAGE

FIGURE 2 – EFFECTS OF FREQUENCY

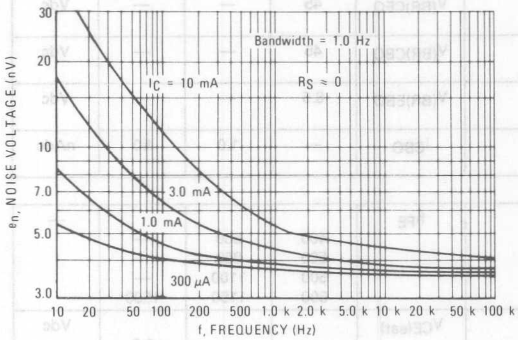


FIGURE 3 – EFFECTS OF COLLECTOR CURRENT

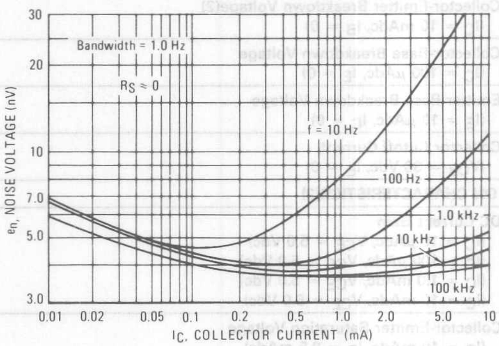


FIGURE 4 – NOISE CURRENT

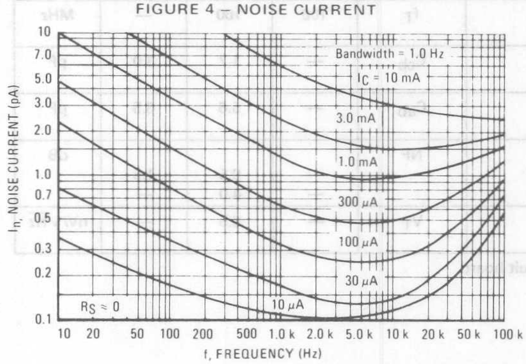
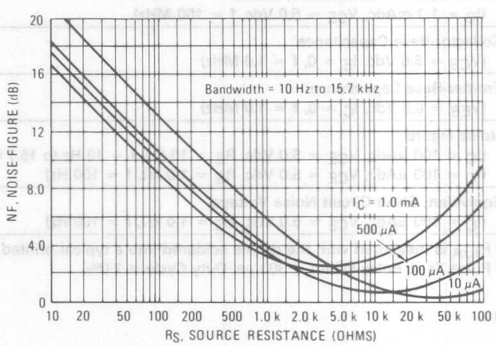


FIGURE 5 – WIDEBAND NOISE FIGURE



100 Hz NOISE DATA

FIGURE 6 – TOTAL NOISE VOLTAGE

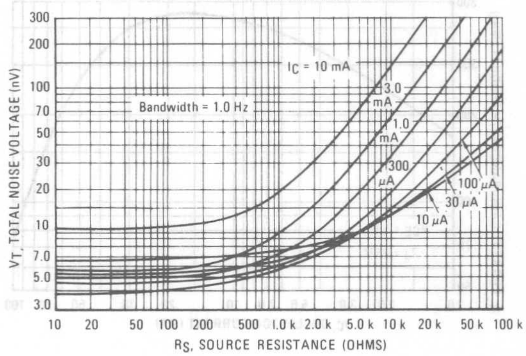


FIGURE 7 – NOISE FIGURE

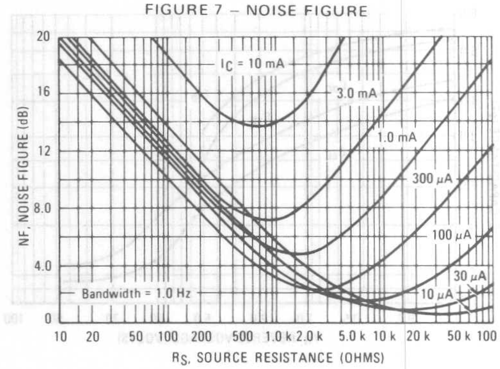


FIGURE 8 — DC CURRENT GAIN

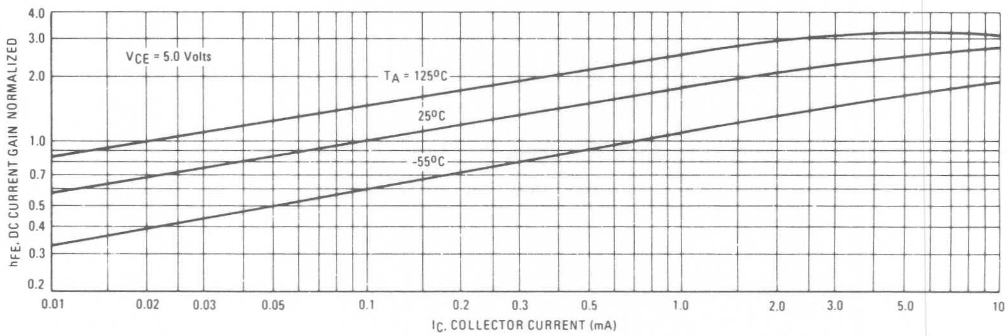


FIGURE 9 – "ON" VOLTAGES

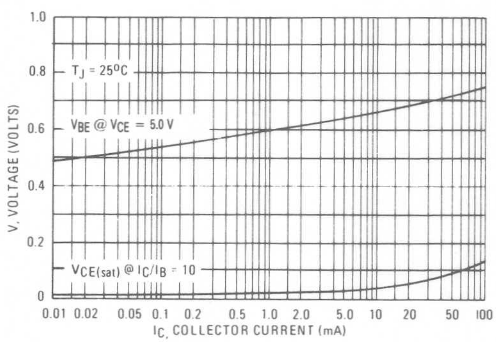
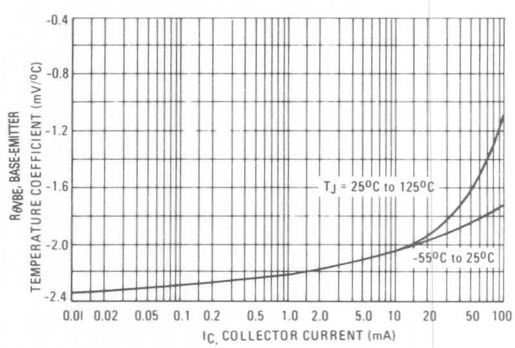


FIGURE 10 – TEMPERATURE COEFFICIENTS



2

FIGURE 11 – CAPACITANCE

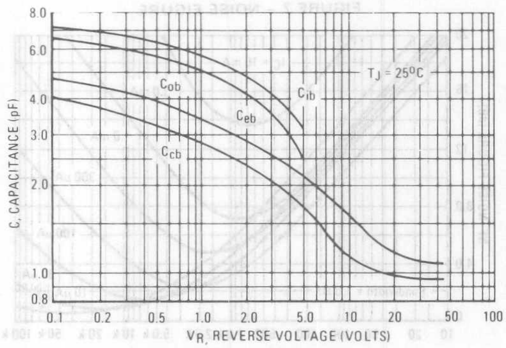
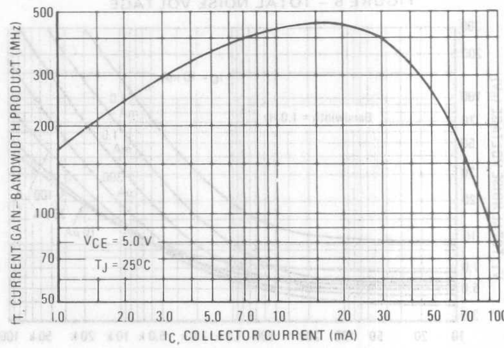
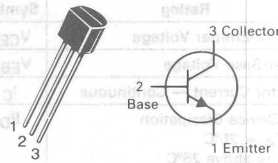


FIGURE 12 – CURRENT-GAIN–BANDWIDTH PRODUCT



MPSA20

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MPS3903 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	4.0	Vdc
Collector Current — Continuous	I_C	100	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	200	°C/W

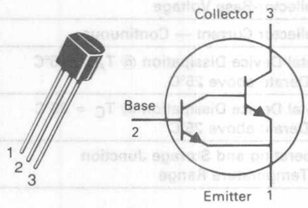
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(2) ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	100	nAdc
ON CHARACTERISTICS				
DC Current Gain(2) ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	40	400	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	0.25	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product(2) ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz	f_T	125	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	4.0	pF

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.
(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MPSA27

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



DARLINGTON TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	MPS-A25	MPS-A26	MPS-A27	Unit
Collector-Emitter Voltage	V_{CES}	40	50	60	Vdc
Emitter-Base Voltage	V_{EBO}		10		Vdc
Collector Current — Continuous	I_C		500		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D		625 5.0		mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−55 to +150		°C

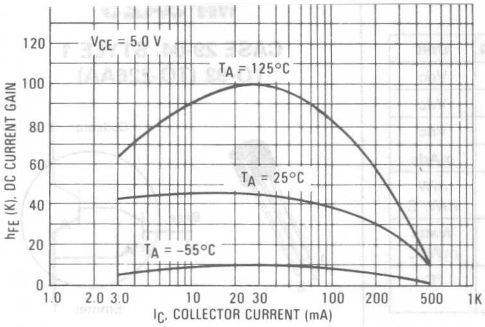
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 100 μAdc, V_{BE} = 0)	MPSA25	$V_{(BR)CES}$	40	—	—	Vdc
	MPSA26		50	—	—	
	MPSA27		60	—	—	
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	MPSA25	$V_{(BR)CBO}$	40	—	—	Vdc
	MPSA26		50	—	—	
	MPSA27		60	—	—	
Collector Cutoff Current (V_{CB} = 30 V, I_E = 0)	MPSA25	I_{CBO}	—	—	100	nAdc
(V_{CB} = 40 V, I_E = 0)	MPSA26		—	—	100	
(V_{CB} = 50 V, I_E = 0)	MPSA27		—	—	100	
Collector Cutoff Current (V_{CE} = 30 V, V_{BE} = 0)	MPSA25	I_{CES}	—	—	500	nAdc
(V_{CE} = 40 V, V_{BE} = 0)	MPSA26		—	—	500	
(V_{CE} = 50 V, V_{BE} = 0)	MPSA27		—	—	500	
Emitter Cutoff Current (V_{BE} = 10 Vdc)		I_{EBO}	—	—	100	nAdc
ON CHARACTERISTICS(1)						
DC Current Gain (I_C = 10 mA, V_{CE} = 5.0 V)		h_{FE}	10,000	—	—	—
(I_C = 100 mA, V_{CE} = 5.0 V)			10,000	—	—	
Collector-Emitter Saturation Voltage (I_C = 100 mA, I_B = 0.1 mAdc)		$V_{CE(sat)}$	—	—	1.5	Vdc
Base-Emitter On Voltage (I_C = 100 mA, V_{CE} = 5.0 Vdc)		$V_{BE(on)}$	—	—	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Small Signal Current Gain (I_C = 10 mA, V_{CE} = 5.0 V, f = 100 MHz)		h_{fe}	1.25	2.4	—	—

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.



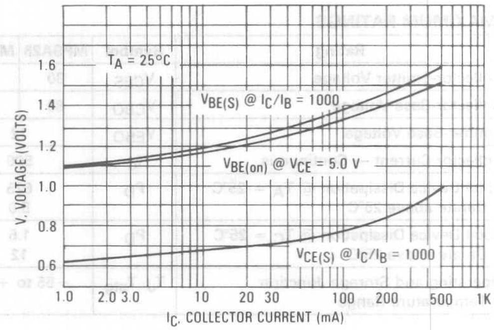


FIGURE 3 — COLLECTOR SATURATION REGION

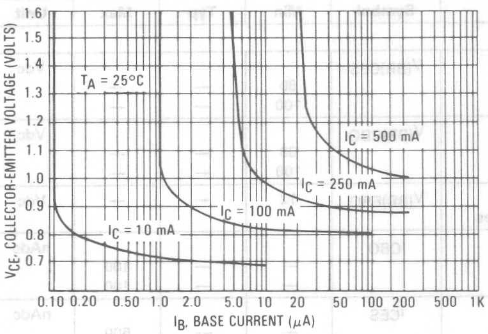


FIGURE 4 — HIGH FREQUENCY CURRENT GAIN

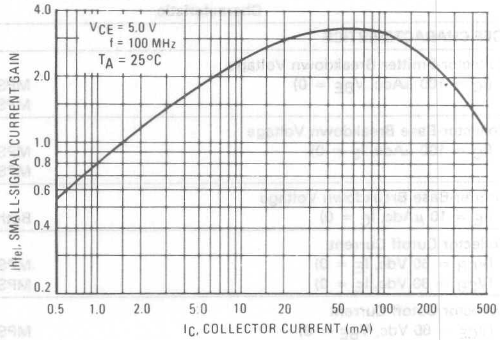
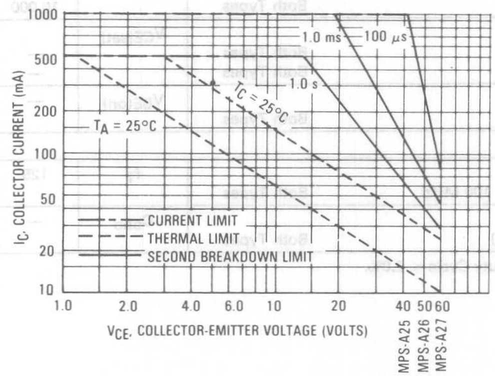
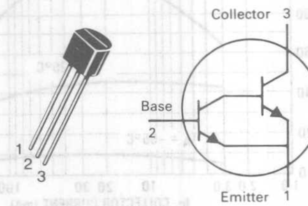


FIGURE 5 — ACTIVE REGION SAFE OPERATING AREA



MPSA28
MPSA29

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



DARLINGTON TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	MPSA28	MPSA29	Unit
Collector-Emitter Voltage	V_{CES}	80	100	Vdc
Collector-Base Voltage	V_{CBO}	80	100	Vdc
Emitter-Base Voltage	V_{EBO}	12		Vdc
Collector Current — Continuous	I_C	500		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage ($I_C = 100\ \mu Adc$, $V_{BE} = 0$)	 MPSA28 MPSA29	$V_{(BR)CES}$	 80 100	 — —	 — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu Adc$, $I_E = 0$)	 MPSA28 MPSA29	$V_{(BR)CBO}$	 80 100	 — —	 — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu Adc$, $I_C = 0$)	Both Types	$V_{(BR)EBO}$	12	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 60$ Vdc, $I_E = 0$) ($V_{CB} = 80$ Vdc, $I_E = 0$)	 MPSA28 MPSA29	I_{CBO}	 — —	 — —	 100 100	nAdc
Collector Cutoff Current ($V_{CE} = 60$ Vdc, $V_{BE} = 0$) ($V_{CE} = 80$ Vdc, $V_{BE} = 0$)	 MPSA28 MPSA29	I_{CES}	 — —	 — —	 500 500	nAdc
Emitter Cutoff Current ($V_{BE} = 10$ Vdc, $I_C = 0$)	Both Types	I_{EBO}	—	—	100	nAdc
ON CHARACTERISTICS(1)						
DC Current Gain ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 5.0$ Vdc)	 Both Types Both Types	h_{FE}	 10,000 10,000	 — —	 — —	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 0.01$ mAdc) ($I_C = 100$ mAdc, $I_B = 0.1$ mAdc)	 Both Types Both Types	$V_{CE(sat)}$	 — —	 0.7 0.8	 1.2 1.5	Vdc
Base-Emitter On Voltage ($I_C = 100$ mAdc, $V_{CE} = 5.0$ Vdc)	Both Types	$V_{BE(on)}$	—	1.4	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product(2) ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc, f = 100 MHz)	Both Types	f_T	125	200	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	Both Types	C_{obo}	—	5.0	8.0	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) $f_T = h_{fe} \cdot f_{test}$.

FIGURE 1 — DC CURRENT GAIN

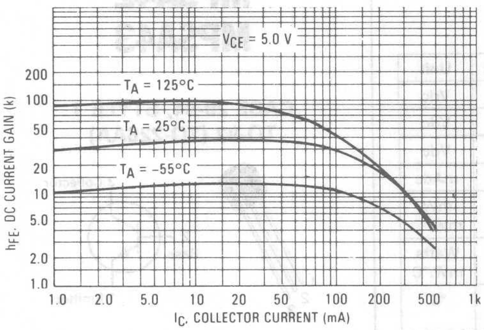


FIGURE 2 — ON VOLTAGES

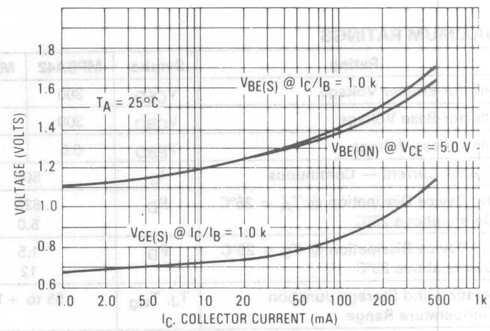


FIGURE 3 — TEMPERATURE COEFFICIENTS

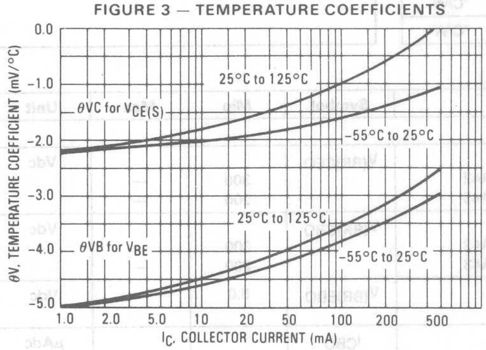


FIGURE 4 — COLLECTOR SATURATION REGION

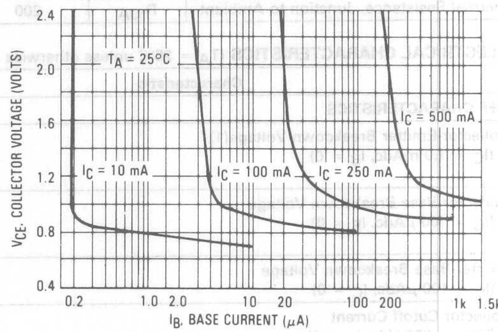


FIGURE 5 — ACTIVE REGION — SAFE OPERATING AREA

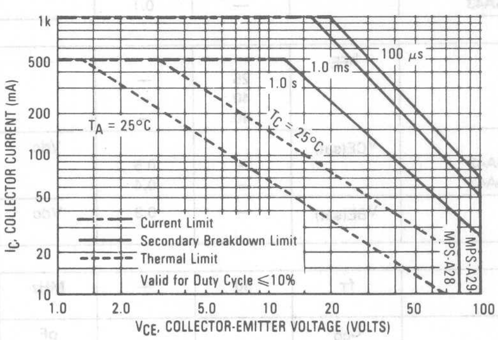
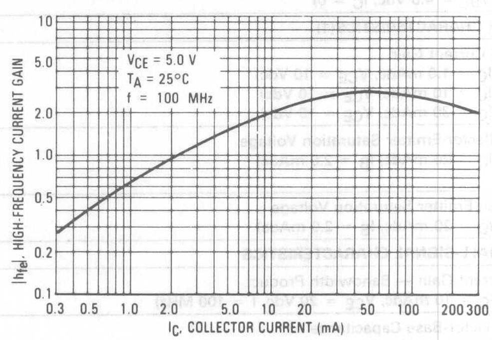


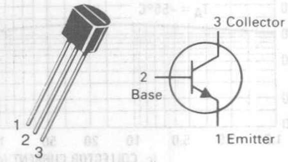
FIGURE 6 — HIGH FREQUENCY CURRENT GAIN



2

MPSA42
MPSA43

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



HIGH VOLTAGE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	MPSA42	MPSA43	Unit
Collector-Emitter Voltage	V_{CEO}	300	200	Vdc
Collector-Base Voltage	V_{CBO}	300	200	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	6.0	Vdc
Collector Current — Continuous	I_C	500		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)	MPSA42 MPSA43	$V_{(BR)CEO}$	300 200	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	MPSA42 MPSA43	$V_{(BR)CBO}$	300 200	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current (V_{CB} = 200 Vdc, I_E = 0) (V_{CB} = 160 Vdc, I_E = 0)	MPSA42 MPSA43	I_{CBO}	— —	0.1 0.1	μAdc
Emitter Cutoff Current (V_{BE} = 6.0 Vdc, I_C = 0) (V_{BE} = 4.0 Vdc, I_C = 0)	MPSA42 MPSA43	I_{EBO}	— —	0.1 0.1	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc) (I_C = 30 mAdc, V_{CE} = 10 Vdc)		h_{FE}	25 40 40	— — —	—
Collector-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)	MPSA42 MPSA43	$V_{CE(sat)}$	— —	0.5 0.4	Vdc
Base-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)		$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)		f_T	50	—	MHz
Collector-Base Capacitance (V_{CB} = 20 Vdc, I_E = 0, f = 1.0 MHz)	MPSA42 MPSA43	C_{cb}	— —	3.0 4.0	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2

FIGURE 1 – DC CURRENT GAIN

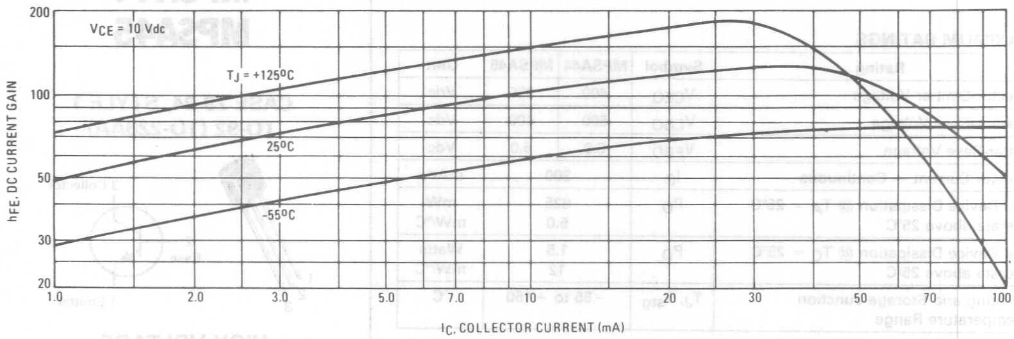


FIGURE 2 – CAPACITANCES

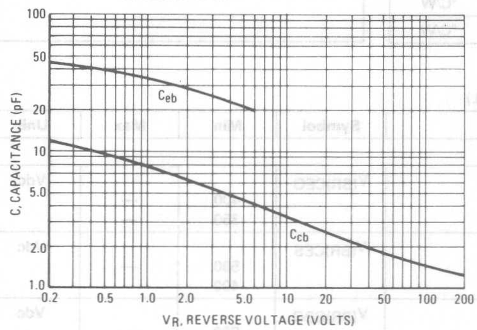


FIGURE 3 – CURRENT-GAIN–BANDWIDTH PRODUCT

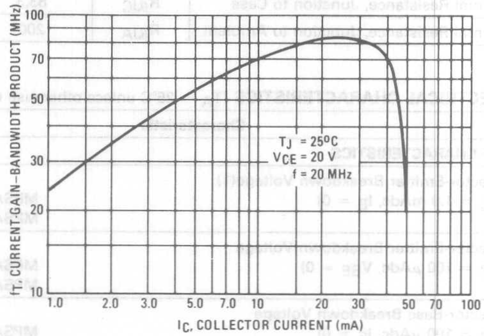


FIGURE 4 – "ON" VOLTAGES

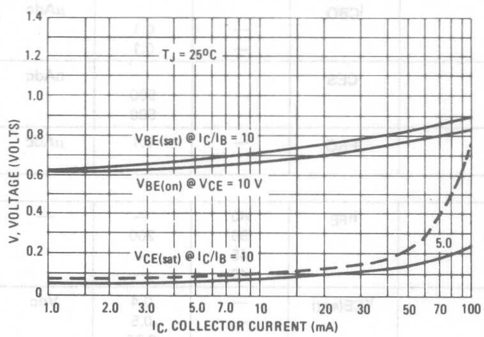
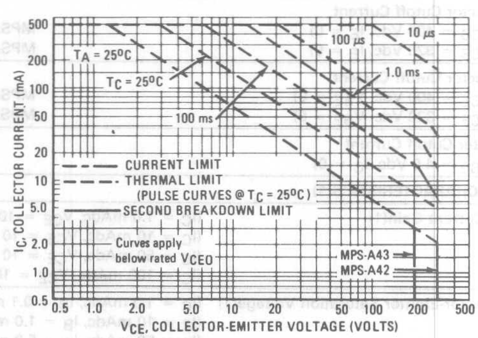
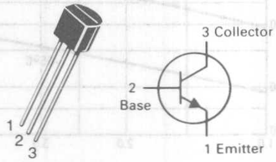


FIGURE 5 – MAXIMUM FORWARD BIAS SAFE OPERATING AREA



MPSA45

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



HIGH VOLTAGE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	MPSA44	MPSA45	Unit
Collector-Emitter Voltage	V_{CEO}	400	350	Vdc
Collector-Base Voltage	V_{CBO}	500	400	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	6.0	Vdc
Collector Current — Continuous	I_C	300		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)	MPSA44 MPSA45	$V_{(BR)CEO}$	400 350	— —	Vdc
Collector-Emitter Breakdown Voltage (I_C = 100 μAdc, V_{BE} = 0)	MPSA44 MPSA45	$V_{(BR)CES}$	500 400	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	MPSA44 MPSA45	$V_{(BR)CBO}$	500 400	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current (V_{CB} = 400 Vdc, I_E = 0) (V_{CB} = 320 Vdc, I_E = 0)	MPSA44 MPSA45	I_{CBO}	— —	0.1 0.1	μAdc
Collector Cutoff Current (V_{CE} = 400 Vdc, V_{BE} = 0) (V_{CE} = 320 Vdc, V_{BE} = 0)	MPSA44 MPSA45	I_{CES}	— —	500 500	nAdc
Emitter Cutoff Current (V_{BE} = 4.0 Vdc, I_C = 0)		I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain(1)	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc) (I_C = 50 mAdc, V_{CE} = 10 Vdc) (I_C = 100 mAdc, V_{CE} = 10 Vdc)	h_{FE}	40 50 45 40	— 200 — —	—
Collector-Emitter Saturation Voltage(1)	(I_C = 1.0 mAdc, I_B = 0.1 mAdc) (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)	$V_{CE(sat)}$	— — —	0.4 0.5 0.75	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{BE(sat)}$	—	0.75	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance (V_{CB} = 20 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	7.0	pF
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	13	pF
Small-Signal Current Gain (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 10 MHz)		h_{fe}	2.0	—	—

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — DC CURRENT GAIN

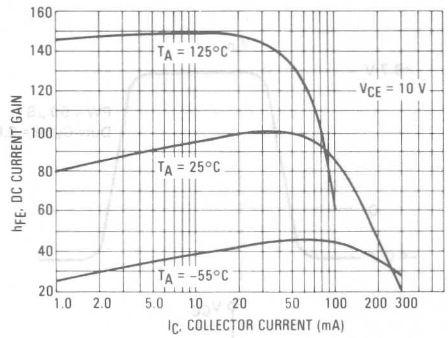


FIGURE 2 — COLLECTOR SATURATION REGION

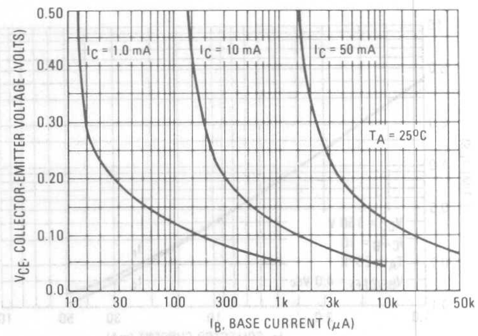


FIGURE 3 — ON VOLTAGES

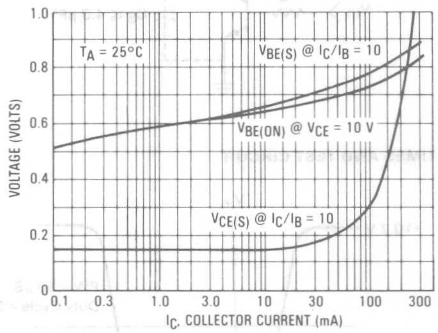


FIGURE 4 — ACTIVE REGION — SAFE OPERATING AREA

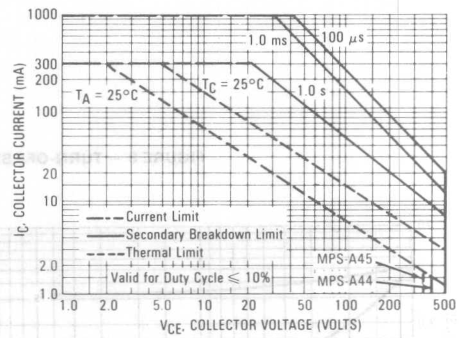


FIGURE 5 — CAPACITANCE

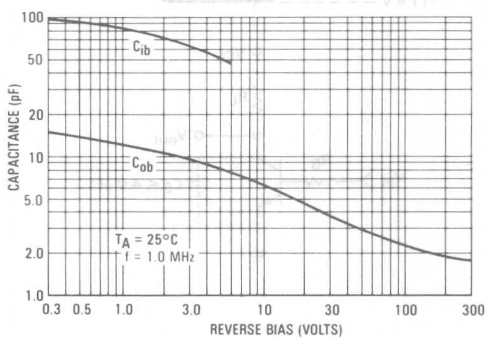
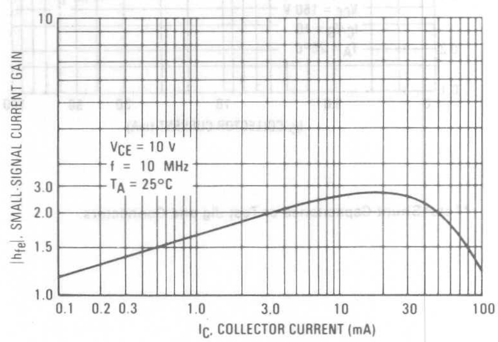


FIGURE 6 — HIGH FREQUENCY CURRENT GAIN



2

FIGURE 7 — TURN-ON SWITCHING TIMES AND TEST CIRCUIT

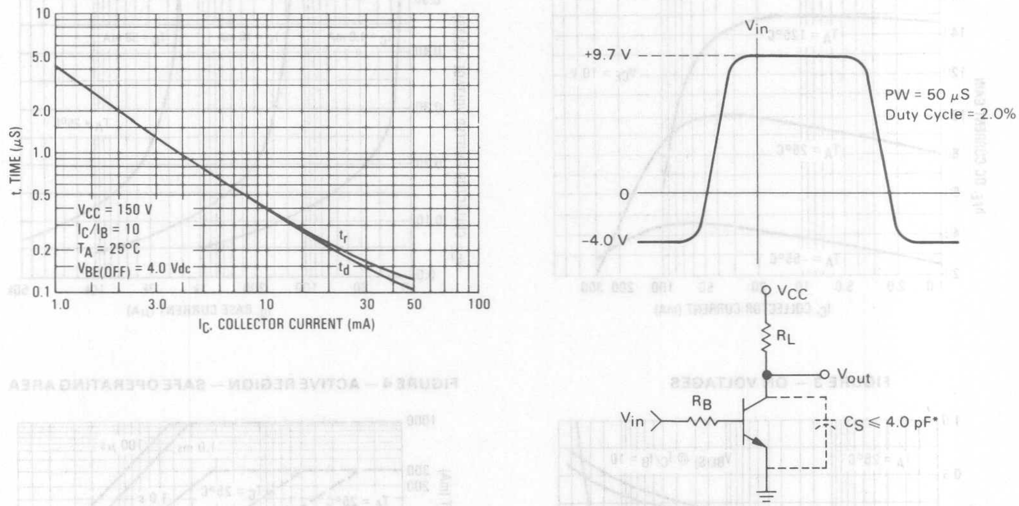
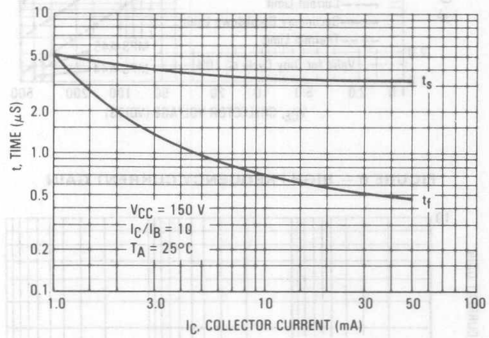
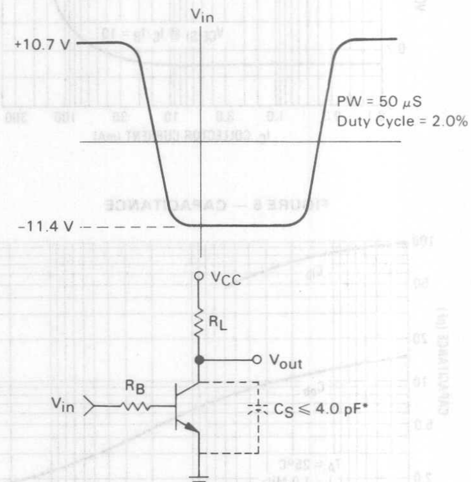


FIGURE 8 — TURN-OFF SWITCHING TIMES AND TEST CIRCUIT

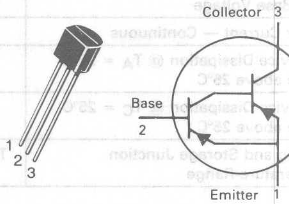




*Total Shunt Capacitance or Test Jig and Connectors.

MPSA63
MPSA64

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



DARLINGTON TRANSISTOR

PNP SILICON

Refer to MPSA75 for graphs.

MAXIMUM RATINGS

Rating	Symbol	MPSA62	MPSA63 MPSA64	Unit
Collector-Emitter Voltage	V_{CES}	20	30	Vdc
Collector-Base Voltage	V_{CBO}	20	30	Vdc
Emitter-Base Voltage	V_{EBO}	10		Vdc
Collector Current — Continuous	I_C	500		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 100 μAdc, V_{BE} = 0)	 MPSA62 MPSA63, MPSA64	$V_{(BR)CES}$	 20 30	 — —	Vdc
Collector Cutoff Current (V_{CB} = 15 Vdc, I_E = 0) (V_{CB} = 30 Vdc, I_E = 0)	 MPSA62 MPSA63, MPSA64	I_{CBO}	 — —	 100 100	nAdc
Emitter Cutoff Current (V_{BE} = 10 Vdc, I_C = 0)		I_{EBO}	—	100	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 10 mAdc, V_{CE} = 5.0 Vdc) (I_C = 100 mAdc, V_{CE} = 5.0 Vdc)	 MPSA63 MPSA64 MPSA62 MPSA63 MPSA64	h_{FE}	 5000 10,000 20,000 10,000 20,000	 — — — —	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.01 mAdc) (I_C = 100 mAdc, I_B = 0.1 mAdc)	 MPSA62 MPSA63, MPSA64	$V_{CE(sat)}$	 — —	 1.0 1.5	Vdc
Base-Emitter On Voltage (I_C = 10 mAdc, V_{CE} = 5.0 Vdc) (I_C = 100 mAdc, V_{CE} = 5.0 Vdc)	 MPSA62 MPSA63, MPSA64	$V_{BE(on)}$	 — —	 1.4 2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 100 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)	 MPSA63, MPSA64	f_T	125	—	MHz

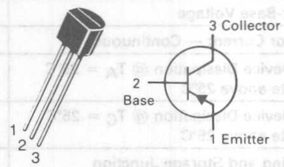
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) $f_T = |h_{fe}| \cdot f_{test}$.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	100	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

MPSA70

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

PNP SILICON

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

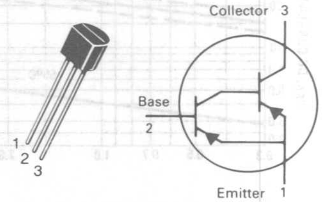
Refer to 2N5086 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40		Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	100	nAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	40	400	
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	0.25	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	125	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	4.0	pF

MPSA75
MPSA77

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



DARLINGTON TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	MPSA75	MPSA77	Unit
Collector-Emitter Voltage	V_{CES}	40	60	Vdc
Emitter-Base Voltage	V_{EBO}	10		Vdc
Collector Current — Continuous	I_C	500		Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 100 μAdc, V_{BE} = 0)	MPSA75 MPSA77	$V_{(BR)CES}$	40 60	— —	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	MPSA75 MPSA77	$V_{(BR)CBO}$	40 60	— —	— —	Vdc
Collector Cutoff Current (V_{CB} = 30 V, I_E = 0) (V_{CB} = 40 V, I_E = 0) (V_{CB} = 50 V, I_E = 0)		I_{CBO}	— — —	— — —	100 — —	nAdc
Collector Cutoff Current (V_{CE} = 30 V, V_{BE} = 0) (V_{CE} = 40 V, V_{BE} = 0) (V_{CE} = 50 V, V_{BE} = 0)		I_{CES}	— — —	— — —	500 — —	nAdc
Emitter Cutoff Current (V_{BE} = 10 Vdc)		I_{EBO}	—	—	100	nAdc
ON CHARACTERISTICS						
DC Current Gain (I_C = 10 mA, V_{CE} = 5.0 V) (I_C = 100 mA, V_{CE} = 5.0 V)		h_{FE}	10,000 10,000	— —	— —	—
Collector-Emitter Saturation Voltage (I_C = 100 mA, I_B = 0.1 mAdc)		$V_{CE(sat)}$	—	—	1.5	Vdc
Base-Emitter On Voltage (I_C = 100 mA, V_{CE} = 5.0 Vdc)		V_{BE}	—	—	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — High Frequency (I_C = 10 mA, V_{CE} = 5.0 V, f = 100 MHz)		$\|h_{fe}\|$	1.25	2.4	—	—

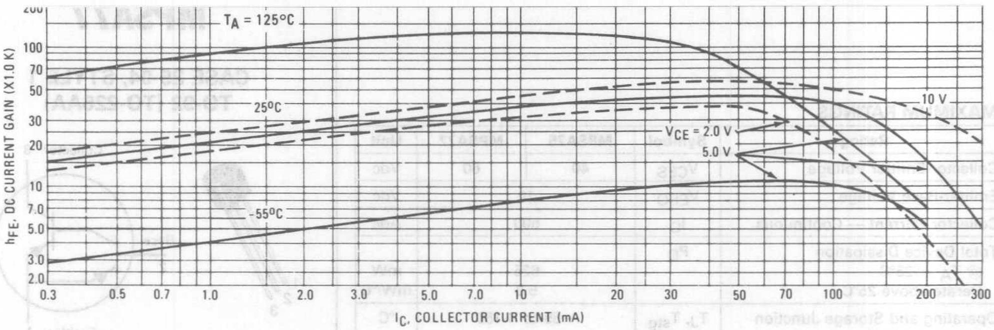


FIGURE 2 — "ON" VOLTAGE

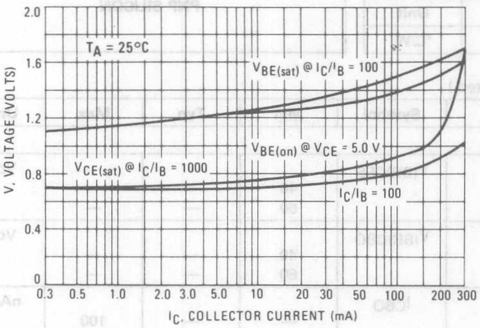


FIGURE 3 — COLLECTOR SATURATION REGION

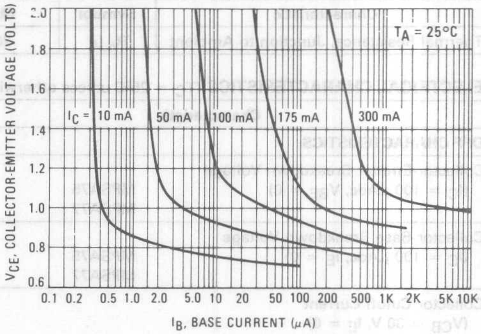


FIGURE 4 — HIGH FREQUENCY CURRENT GAIN

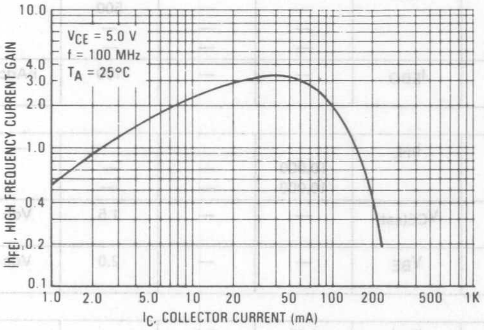
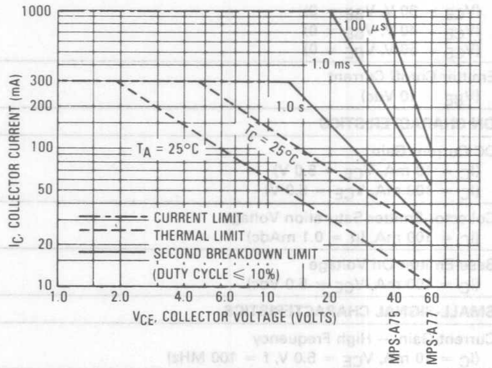
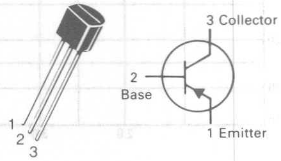


FIGURE 5 — ACTIVE REGION, SAFE OPERATING AREA



MPSA93

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



HIGH VOLTAGE TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	MPSA92	MPSA93	Unit
Collector-Emitter Voltage	V_{CEO}	300	200	Vdc
Collector-Base Voltage	V_{CBO}	300	200	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)	MPSA92 MPSA93	$V_{(BR)CEO}$	300 200	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	MPSA92 MPSA93	$V_{(BR)CBO}$	300 200	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 200 Vdc, I_E = 0) (V_{CB} = 160 Vdc, I_E = 0)	MPSA92 MPSA93	I_{CBO}	—	0.25 0.25	μAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)		I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc) (I_C = 30 mAdc, V_{CE} = 10 Vdc)	Both Types Both Types MPSA92 MPSA93	h_{FE}	25 40 25 25	— — — —	—
Collector-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)	MPSA92 MPSA93	$V_{CE(sat)}$	— —	0.5 0.4	Vdc
Base-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)		$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)		f_T	50	—	MHz
Collector-Base Capacitance (V_{CB} = 20 Vdc, I_E = 0, f = 1.0 MHz)	MPSA92 MPSA93	C_{cb}	— —	6.0 8.0	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 – DC CURRENT GAIN

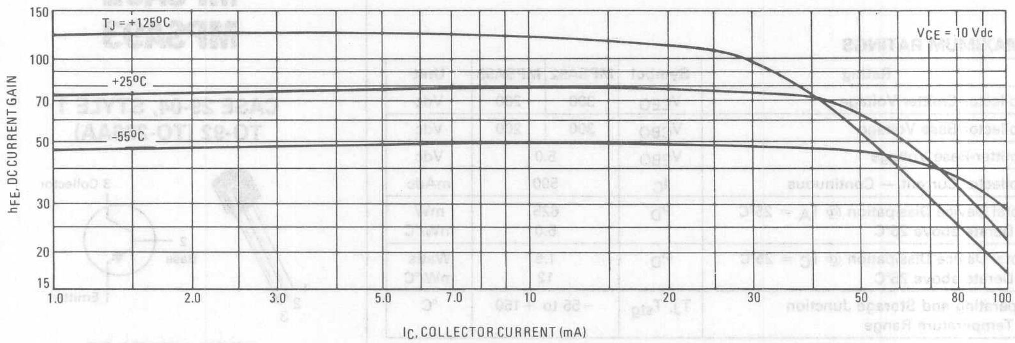


FIGURE 2 – CAPACITANCES

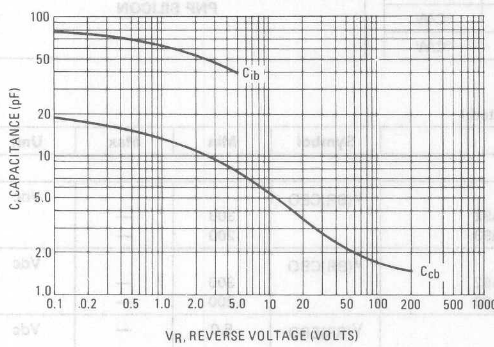


FIGURE 3 – CURRENT-GAIN–BANDWIDTH PRODUCT

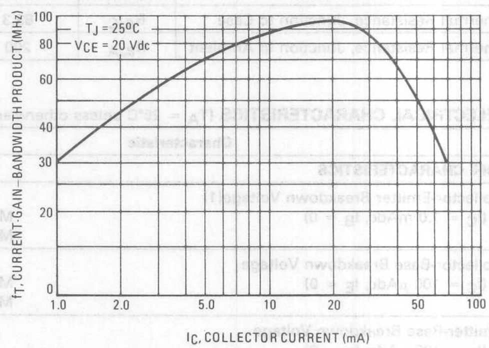


FIGURE 4 – "ON" VOLTAGES

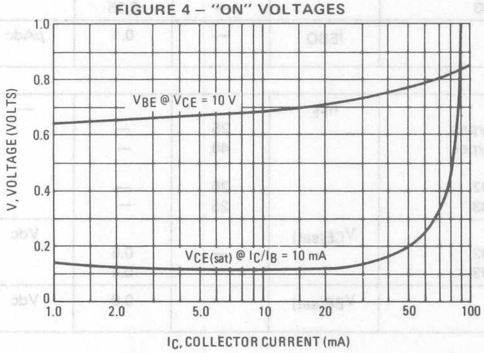
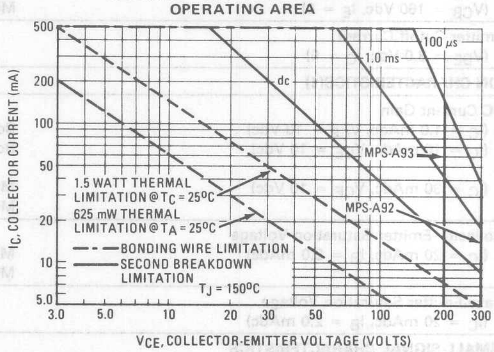
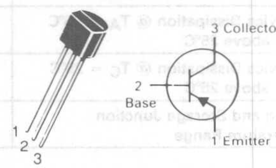


FIGURE 5 – ACTIVE-REGION SAFE OPERATING AREA



MPSD55

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

PNP SILICON

Refer to 2N4400 for MPSD05 graphs.*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	25	Vdc
Collector Current — Continuous	I_C	600	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient(1)	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

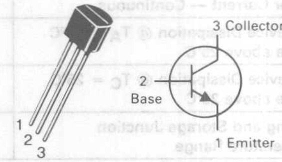
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	25	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	25	—	Vdc
Collector Cutoff Current ($V_{CE} = 20$ Vdc)	I_{CEO}	—	1.0	μAdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$)	I_{CBO}	—	1.0	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	100	nAdc
ON CHARACTERISTICS(2)				
DC Current Gain ($I_C = 50$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 500$ mAdc, $V_{CE} = 5.0$ Vdc)	h_{FE}	 50 80 30	 — — —	—
Collector-Emitter Saturation Voltage ($I_C = 100$ mAdc, $I_B = 10$ mAdc)	$V_{CE(sat)}$	—	0.5	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	100	—	MHz

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.
(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
*Refer to 2N4402 for MPSD55 graphs.

2

MPSH04

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	80	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	100	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	200	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

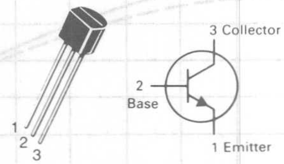
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	80	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	80	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 60$ Vdc, $I_E = 0$)	I_{CBO}	—	—	50	nAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 1.5$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	30	—	120	
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	—	0.25	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Crrent-Gain — Bandwidth Product ($I_C = 1.5$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	80	—	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, f = 1.0 MHz)	C_{cb}	—	—	1.6	pF
Output Admittance ($I_C = 1.5$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{oe}	—	—	5.0	μmhos
Noise Figure ($I_C = 1.5$ mAdc, $V_{CE} = 10$ Vdc, $R_S = 50$ ohms, f = 1.0 MHz) MPSH04	NF	—	—	2.0	dB

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MPSH07

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



FM/VHF TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	350 2.81	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	357	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	30	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	30	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_E = 0$)	I_{CBO}	—	50	nAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 3.0$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	20	—	—
Base-Emitter On Voltage ($I_C = 3.0$ mAdc, $V_{CE} = 10$ Vdc)	$V_{BE(on)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 3.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	400	—	MHz
Collector-Emitter Capacitance ($V_{CE} = 10$ Vdc, $I_B = 0$, f = 1.0 MHz, base guarded)	C_{ce} (C_{rb})	—	0.3	pF
Noise Figure ($I_C = 3.0$ mAdc, $V_{CB} = 10$ Vdc, $R_S = 50$ Ohms, f = 100 MHz)	NF	—	3.0	dB
FUNCTIONAL TEST				
Common-Emitter Amplifier Power Gain ($I_C = 3.0$ mAdc, $V_{CB} = 10$ Vdc, $R_S = 50$ Ohms, f = 100 MHz) ($I_C = 3.0$ mAdc, $V_{CB} = 10$ Vdc, $R_S = 50$ Ohms, f = 200 MHz)	G_{pb}	 18 14	 — —	dB
Forward AGC Current (Gain Reduction = 30 dB, $R_S = 50$ Ohms, f = 100 MHz)	I_{AGC}	6.5	8.5	mAdc

AGC CHARACTERISTICS

V_{CC} = 10 Vdc, R_S = 50 Ohms, See Figure 9

—— f = 100 MHz – – – f = 200 MHz

FIGURE 1 – POWER GAIN

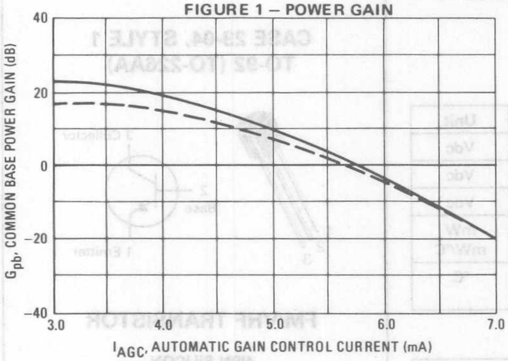
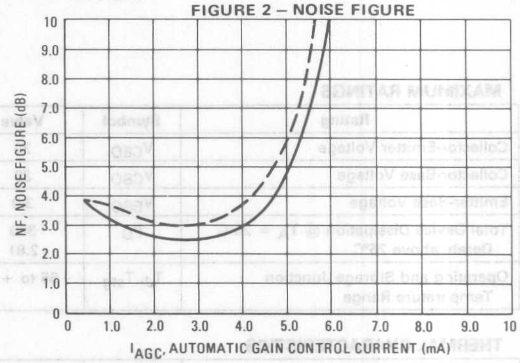


FIGURE 2 – NOISE FIGURE



COMMON-BASE y PARAMETERS

V_{CB} = 10 Vdc, T_A = 25°C

—— f = 100 MHz – – – f = 200 MHz

FIGURE 3 – INPUT ADMITTANCE

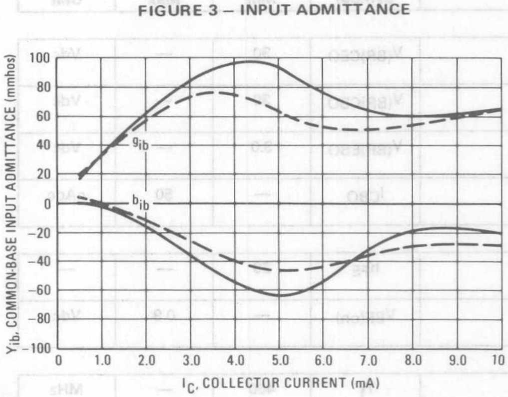


FIGURE 4 – REVERSE TRANSFER ADMITTANCE

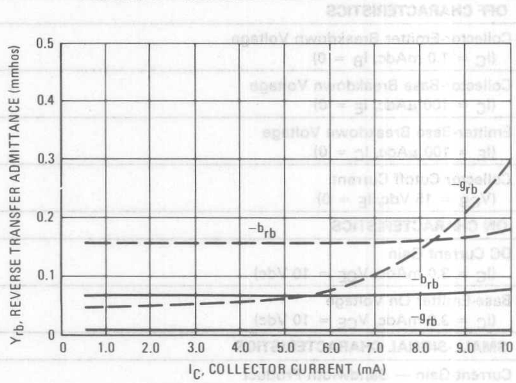


FIGURE 5 – FORWARD TRANSFER ADMITTANCE

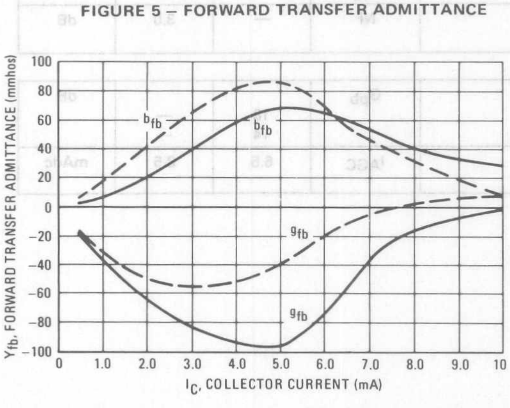


FIGURE 6 – OUTPUT ADMITTANCE

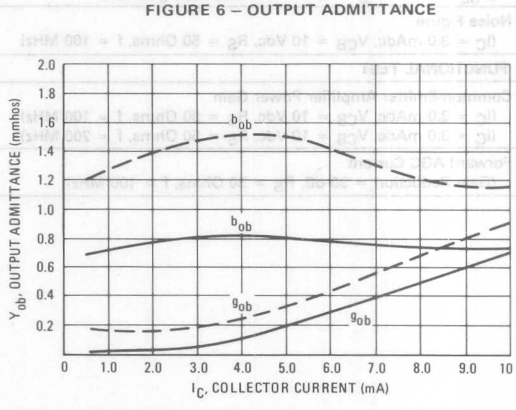


FIGURE 7 — COLLECTOR-BASE TIME CONSTANT

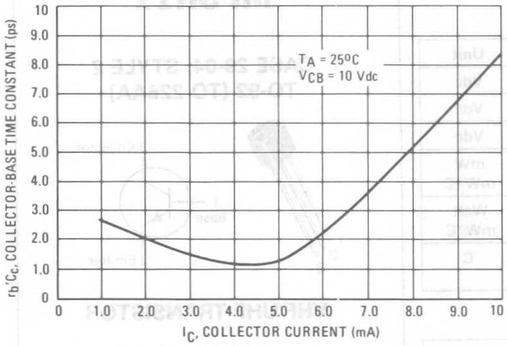


FIGURE 8 — CURRENT-GAIN BANDWIDTH PRODUCT

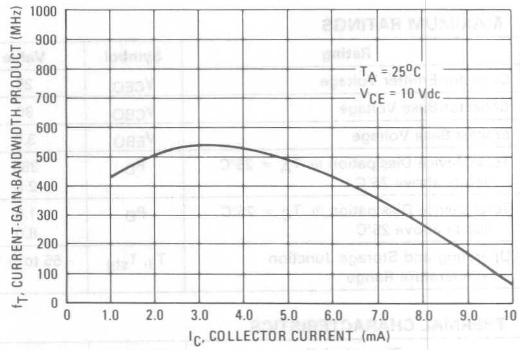
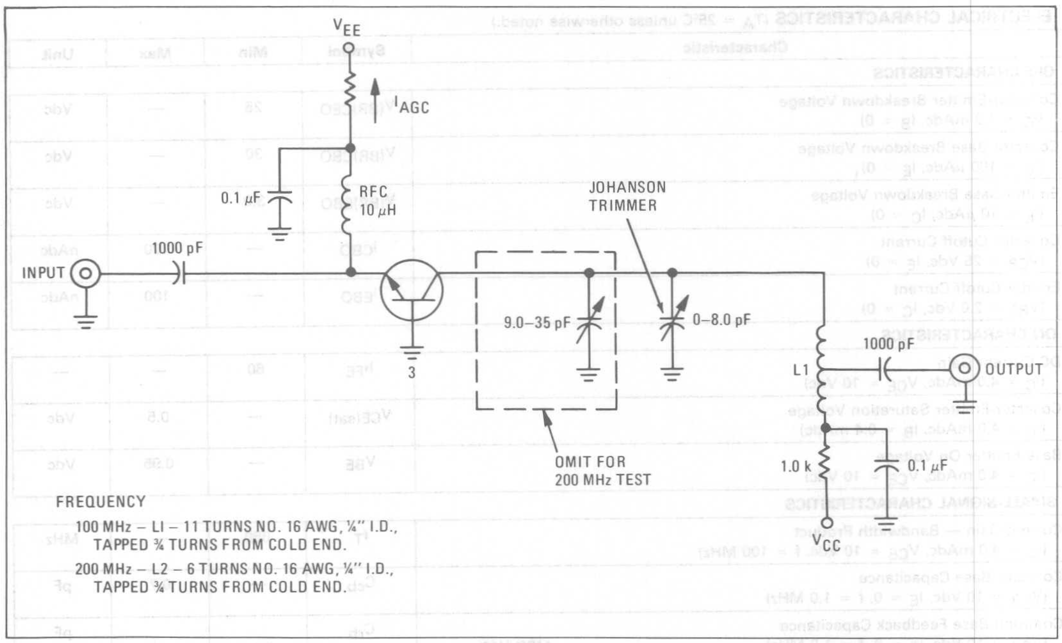


FIGURE 9 — 100-MHz AND 200-MHz COMMON-BASE AMPLIFIER



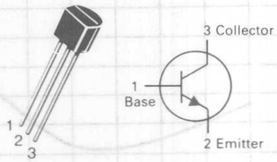
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	350 2.8	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W

CASE 29-04, STYLE 2
TO-92 (TO-226AA)



VHF/UHF TRANSISTOR

NPN SILICON

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	25	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	30	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 25$ Vdc, $I_E = 0$)	I_{CBO}	—	100	nAdc
Emitter Cutoff Current ($V_{BE} = 2.0$ Vdc, $I_C = 0$)	I_{EBO}	—	100	nAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	60	—	—
Collector-Emitter Saturation Voltage ($I_C = 4.0$ mAdc, $I_B = 0.4$ mAdc)	$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter On Voltage ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc)	V_{BE}	—	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	650		MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{cb}		0.7	pF
Common-Base Feedback Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz) MPS-H10 MPS-H11	C_{rb}	0.35 0.6	0.65 0.9	pF
Collector Base Time Constant ($I_C = 4.0$ mAdc, $V_{CB} = 10$ Vdc, f = 31.8 MHz)	$r_b'C_c$	—	9.0	ps

COMMON-BASE y PARAMETERS versus FREQUENCY

(V_{CB} = 10 Vdc, I_C = 4.0 mAdc, T_A = 25°C)

y_{ib}, INPUT ADMITTANCE

FIGURE 1 – RECTANGULAR FORM

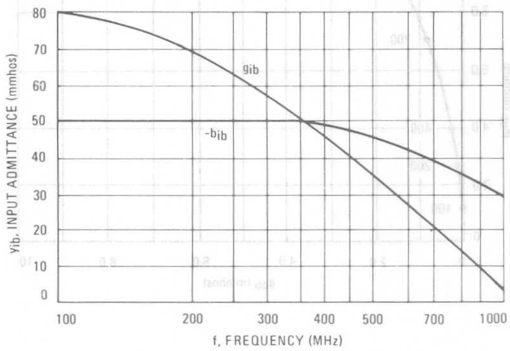
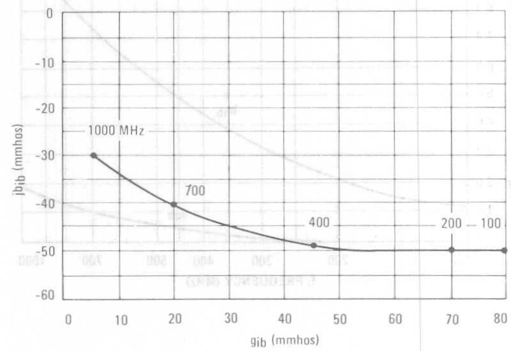


FIGURE 2 – POLAR FORM



COMMON-BASE y PARAMETERS versus FREQUENCY

(V_{CB} = 10 Vdc, I_C = 4.0 mAdc, T_A = 25°C)

y_{fb}, FORWARD TRANSFER ADMITTANCE

FIGURE 3 – RECTANGULAR FORM

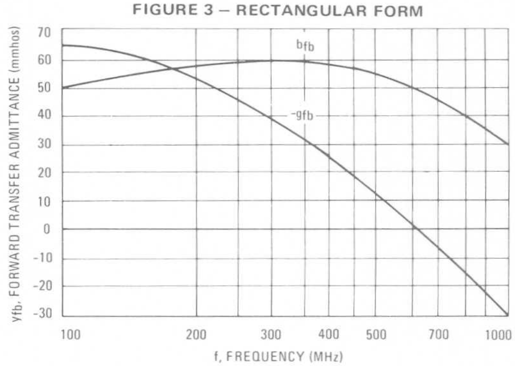
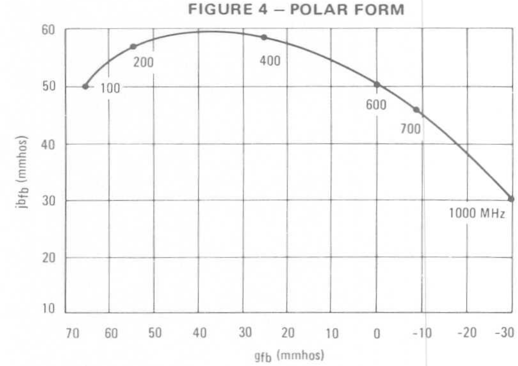


FIGURE 4 – POLAR FORM



y_{rb}, REVERSE TRANSFER ADMITTANCE

FIGURE 5 – RECTANGULAR FORM

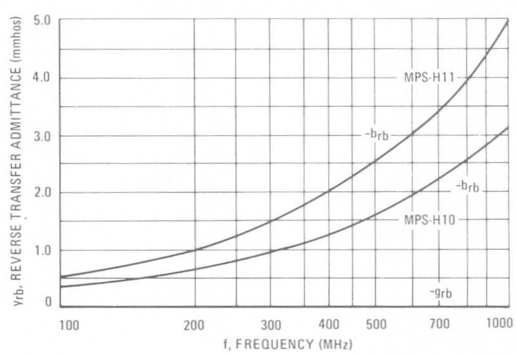
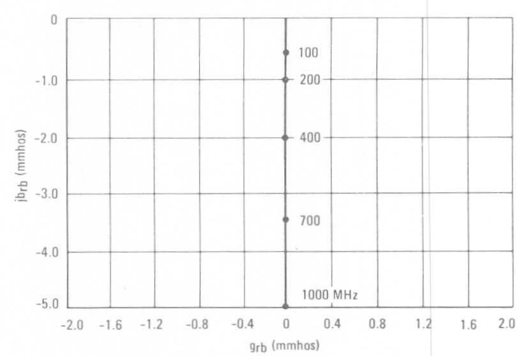


FIGURE 6 – POLAR FORM



2

y_{ob}, OUTPUT ADMITTANCE

FIGURE 7 – RECTANGULAR FORM

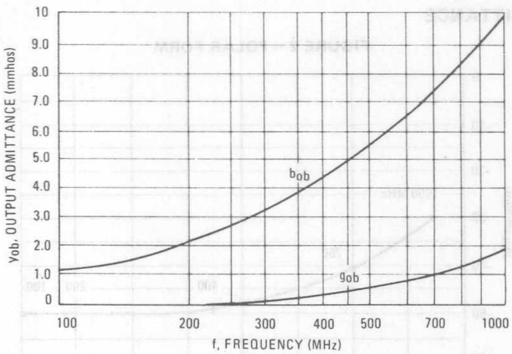
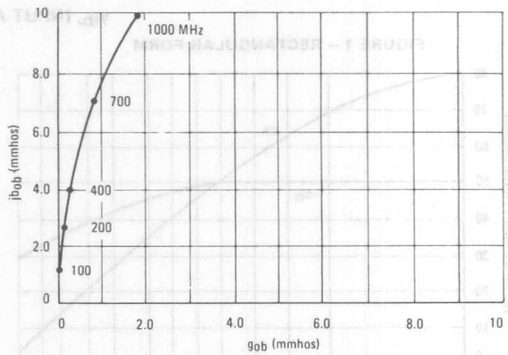
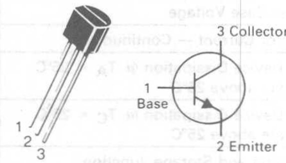


FIGURE 8 – POLAR FORM



MPSH17

CASE 29-04, STYLE 2
TO-92 (TO-226AA)



CATV TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Base Voltage	V_{CBO}	20	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

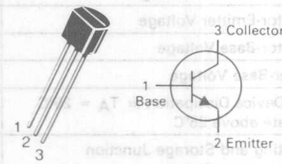
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient (Printed Circuit Board Mounting)	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	15	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	20	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_E = 0$)	I_{CBO}	—	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	25	—	250	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	—	0.5	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	800	—	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, f = 1.0 MHz)	C_{cb}	0.3	—	0.9	pF
Small-Signal Current Gain ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	30	—	—	—
Noise Figure ($I_C = 5.0$ mAdc, $V_{CC} = 12$ Vdc, $R_S = 50$ ohms, f = 200 MHz)	NF	—	—	6.0	dB
FUNCTIONAL TEST					
Amplifier Power Gain ($I_C = 5.0$ mAdc, $V_{CC} = 12$ Vdc, $R_S = 50$ ohms, f = 200 MHz)	G_{pe}	—	24	—	dB

MPSH20

CASE 29-04, STYLE 2
TO-92 (TO-226AA)



VHF TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	100	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	350 2.81	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.0 8.0	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_E = 0$)	I_{CBO}	—	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	25	—	—	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	400	620	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{cb}	—	0.5	0.65	pF
Collector Base Time Constant ($I_E = 4.0$ mAdc, $V_{CB} = 10$ Vdc, f = 31.8 MHz)	$rb'C_c$	—	10	—	ps
Conversion Gain (213 to 45 MHz) ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc, Oscillator Injection = 200 mVdc)	—	18	23	—	dB

2

CONVERSION GAIN CHARACTERISTICS
(TEST CIRCUIT FIGURE 9)

FIGURE 1 – VARIATION WITH COLLECTOR CURRENT

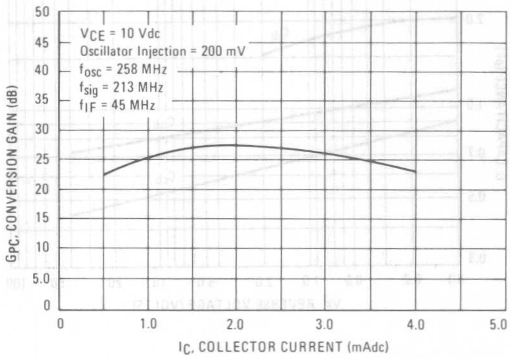
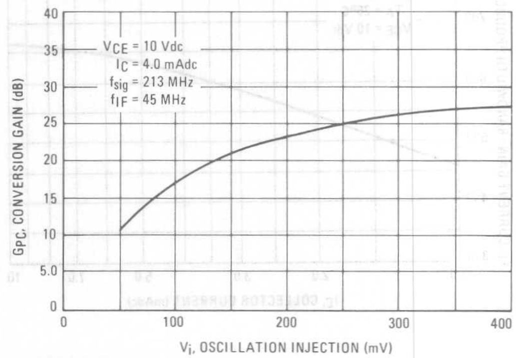


FIGURE 2 – VARIATION WITH INJECTION LEVEL



COMMON-EMITTER y PARAMETERS
(I_C = 4.0 mAdc, V_{CE} = 10 Vdc, T_A = 25°C)

FIGURE 3 – INPUT ADMITTANCE

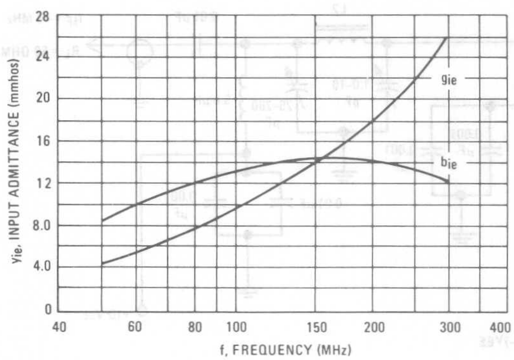
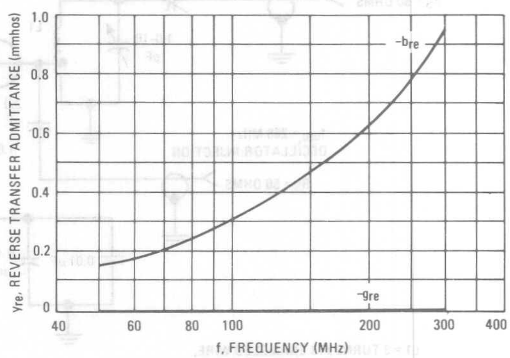


FIGURE 4 – REVERSE TRANSFER ADMITTANCE



COMMON-EMITTER y PARAMETERS
(I_C = 4.0 mAdc, V_{CE} = 10 Vdc, T_A = 25°C)

FIGURE 5 – FORWARD TRANSFER ADMITTANCE

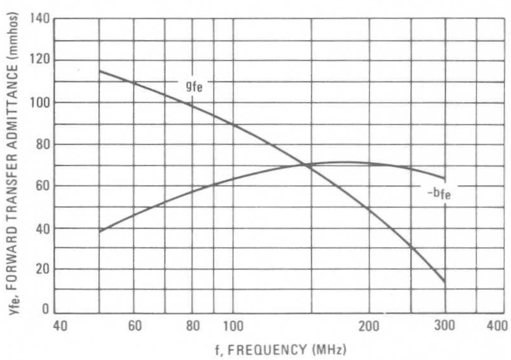
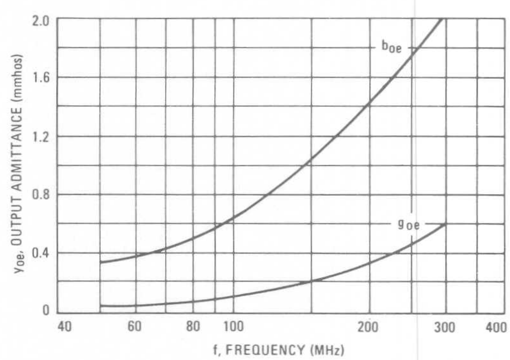


FIGURE 6 – OUTPUT ADMITTANCE



2

FIGURE 7 – CURRENT-GAIN–BANDWIDTH PRODUCT

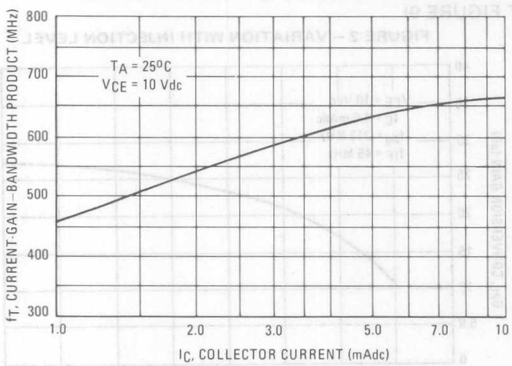


FIGURE 8 – CAPACITANCES

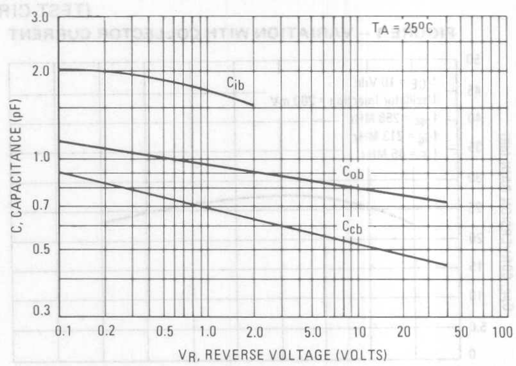
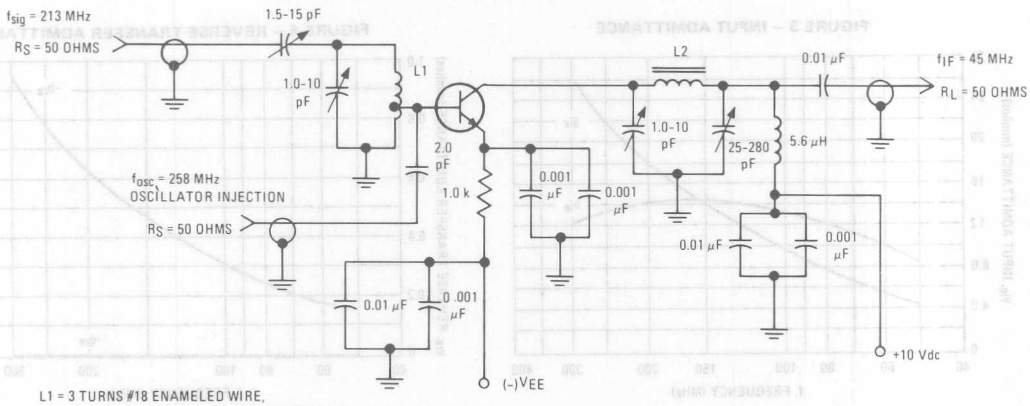


FIGURE 9 – MIXER TEST CIRCUIT

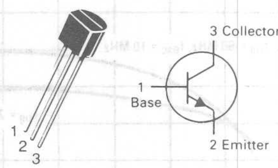


L1 = 3 TURNS #18 ENAMELED WIRE,
1/4" I.D., AIR WOUND, WINDING LENGTH 1/2";
BASE TAPPED 1 TURN FROM GROUND.

L2 = 10 TURNS #26 INSULATED WIRE, WOUND
ON 1/4" I.D. COIL FORM, ARNOLD PART
NO. A1-10 IRON POWDER CORE.

MPSH24

CASE 29-04, STYLE 2
TO-92 (TO-226AA)



VHF TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	100	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	350 2.8	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +135	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_E = 0$)	I_{CBO}	—	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 8.0$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	30	—	—	—
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 8.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	400	620	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{cb}	—	0.25	0.36	pF
Conversion Gain	—				dB
(213 MHz to 45 MHz) ($I_C = 8.0$ mAdc, $V_{CC} = 20$ Vdc, Oscillator Injection = 150 mVrms)		19	24	—	
(60 MHz to 45 MHz) ($I_C = 8.0$ mAdc, $V_{CC} = 20$ Vdc, Oscillator Injection = 150 mVrms)		24	29	—	

2

CONVERSION GAIN CHARACTERISTICS
(TEST CIRCUIT FIGURE 7)
(V_{CC} = 20 Vdc, $R_S = R_L$ = 50 Ohms, f_{if} = 44 MHz, B.W. = 6.0 MHz)

FIGURE 1 – CONVERSION GAIN versus COLLECTOR CURRENT

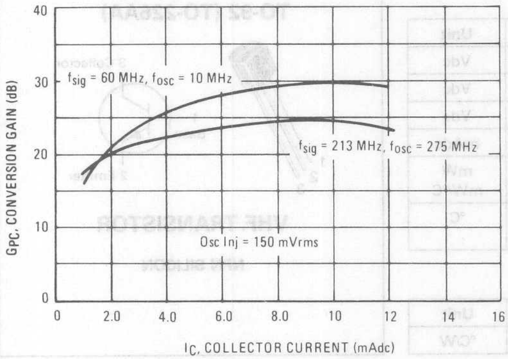
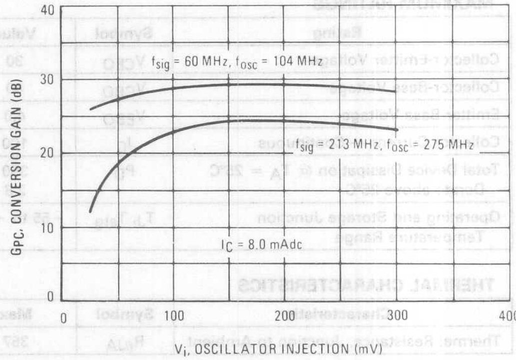


FIGURE 2 – CONVERSION GAIN versus INJECTION LEVEL



COMMON-EMITTER y PARAMETERS
(V_{CE} = 15 Vdc, T_A = 25°C)

FIGURE 3 – INPUT ADMITTANCE

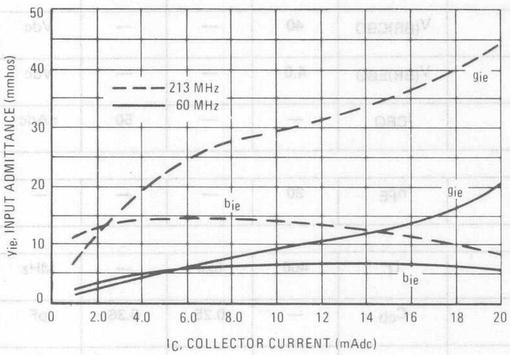


FIGURE 4 – REVERSE TRANSFER ADMITTANCE

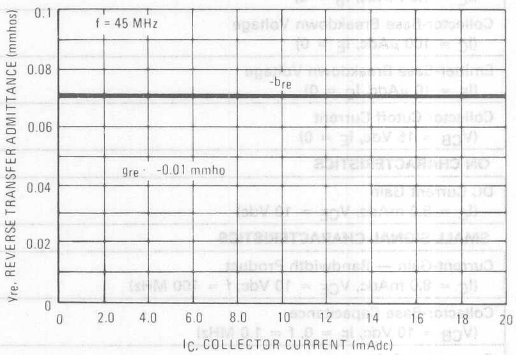


FIGURE 5 – FORWARD TRANSFER ADMITTANCE

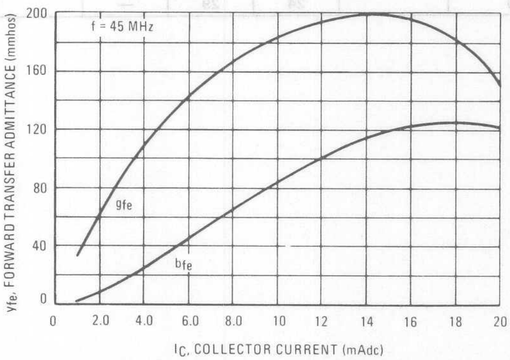
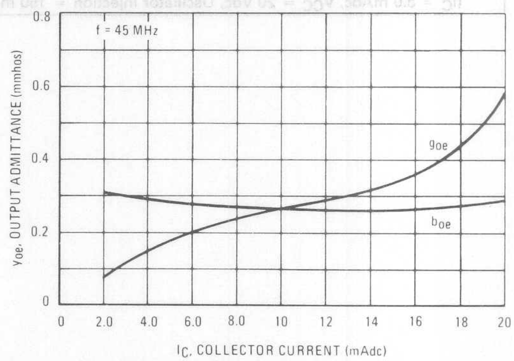
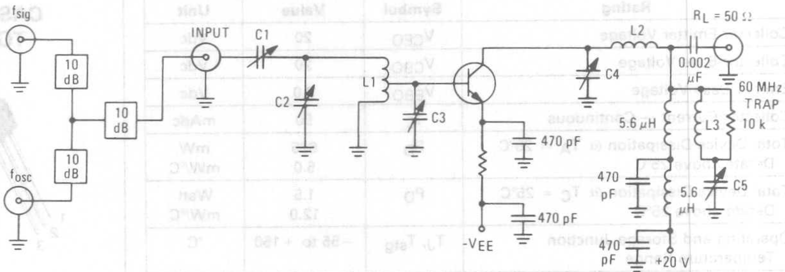


FIGURE 6 – OUTPUT ADMITTANCE



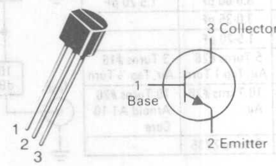
f_{sig}	60 MHz	213 MHz
f_{osc}	105 MHz	258 MHz
C1	1.5-20 pF	1.5-20 pF
C2	8.0-60 pF	6.0-12 pF
C3	8.0-60 pF	1.5-20 pF
C4	3.0-35 pF	–
C5	1.5-20 pF	–
L1	5 Turns #26 Air, Tap 1 Turn	3 Turns #16 Air, Tap ½ Turn
L2	10 Turns #26 Air	10 Turns #26 Arnold A1-10 Core
L3	Ohmite Z235	–



2

MPSH30

CASE 29-04, STYLE 2
TO-92 (TO-226AA)



IF AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	20	Vdc
Collector-Base Voltage	V_{CBO}	20	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	50	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	200	°C/W

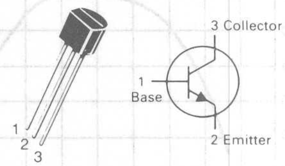
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	20	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	20	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 10$ Vdc, $I_E = 0$)	I_{CBO}	—	50	nAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 4.0$ mAdc, $V_{CE} = 5.0$ Vdc)	h_{FE}	20	200	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 5.0$ mAdc)	$V_{CE(sat)}$	0.1	3.0	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 5.0$ mAdc)	$V_{BE(sat)}$	—	0.96	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	300	800	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz, emitter guarded)	C_{cb}	—	0.65	pF
Noise Figure ($V_{AGC} = 2.75$ Vdc, $R_S = 50$ ohms, f = 45 MHz)	NF	—	6.0	dB
FUNCTIONAL TESTS				
Power Gain ($V_{AGC} = 2.75$ Vdc, $R_S = 50$ ohms, f = 45 MHz)	G_{pe}	22.5	31	dB
Forward AGC Voltage (Gain Reduction = 30 dB, $R_S = 50$ ohms, f = 45 MHz)	V_{AGC}	4.4	5.4	Vdc

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

MPSH32

CASE 29-04, STYLE 2
TO-92 (TO-226AA)



VHF TRANSISTOR

NPN SILICON

2

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +135	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 10$ Vdc, $I_E = 0$)	I_{CBO}	—	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 4.0$ mAdc, $V_{CE} = 5.0$ Vdc)	h_{FE}	27	35	200	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 5.0$ mAdc)	$V_{CE(sat)}$	—	1.5	3.0	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 5.0$ mAdc)	$V_{BE(sat)}$	—	0.9	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	300	440	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz) (Emitter Guarded)	C_{cb}	—	0.2	0.22	pF
Noise Figure ($I_E \approx 4.0$ mAdc, $V_{CE} \approx 9.3$ Vdc, $V_{AGC} = 2.75$ Vdc, $R_S = 50$ Ohms, f = 45 MHz)	NF	—	3.3	—	dB
FUNCTIONAL TEST					
Amplifier Power Gain ($I_E \approx 4.0$ mAdc, $V_{CE} \approx 9.3$ Vdc, $V_{AGC} = 2.75$ Vdc, $R_S = 50$ Ohms, f = 45 MHz)	G_{pe}	22.5	25	—	dB
Forward AGC Voltage (Gain Reduction = 30 dB, $R_S = 50$ Ohms, f = 45 MHz)	V_{AGC}	—	5.5	—	Vdc
SUMMARY-COMMON EMITTER PARAMETERS ($V_{CE} = 10$ Vdc, $I_C = 4.0$ mAdc, f = 45 MHz)					
Input Conductance	g_{ie}	—	6.0	—	mmhos
Input Capacitance	C_{ieo}	—	33	—	pF
Forward Transfer Admittance Magnitude	$\|y_{fe}\|$	—	110	—	mmhos
Forward Transfer Admittance Phase Angle	$\angle y_{fe}$	—	−22	—	Degrees
Feedback Capacitance	C_{re}	—	0.2	—	pF
Output Conductance	g_{oe}	—	20	—	μmhos
Output Capacitance	C_{oe}	—	1.4	—	pF
Maximum Unilateralized Power Gain $G_{um} = \frac{\|y_{fe}\|^2}{4\,g_{ie}\,g_{oe}}$	G_{um}	—	44	—	dB

2

AGC CHARACTERISTICS

V_{CC} = 12 Vdc, R_S = 50 Ohms, f = 45 MHz, See Figure 10

FIGURE 1 – POWER GAIN

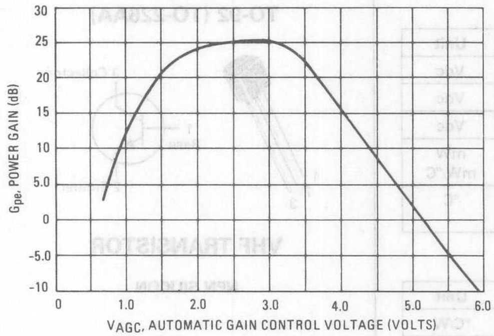
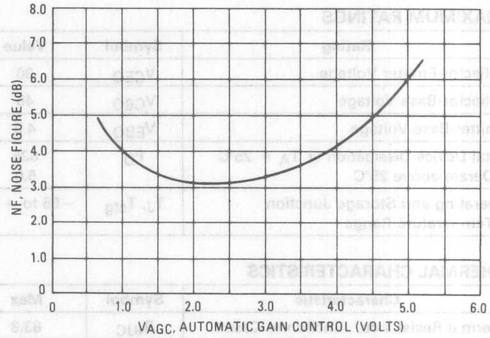


FIGURE 2 – NOISE FIGURE



COMMON-EMITTER y PARAMETERS

V_{CE} = 10 Vdc, f = 45 MHz, T_A = 25°C

FIGURE 3 – INPUT ADMITTANCE

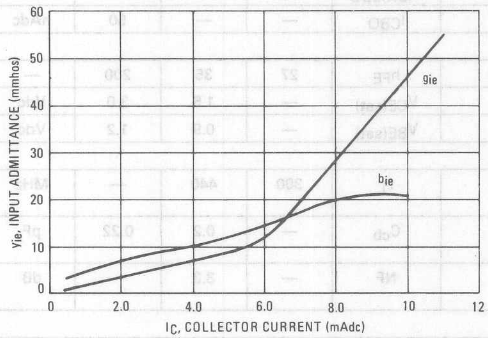


FIGURE 4 – REVERSE TRANSFER ADMITTANCE

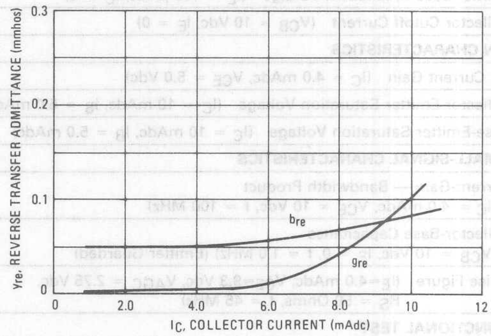


FIGURE 5 – FORWARD TRANSFER ADMITTANCE

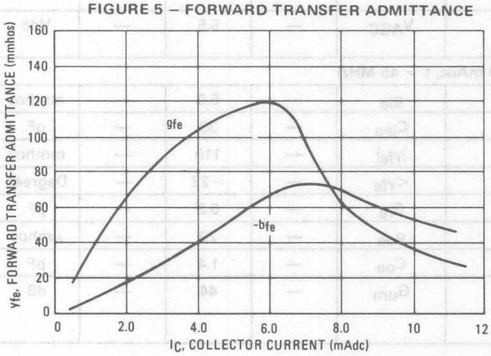
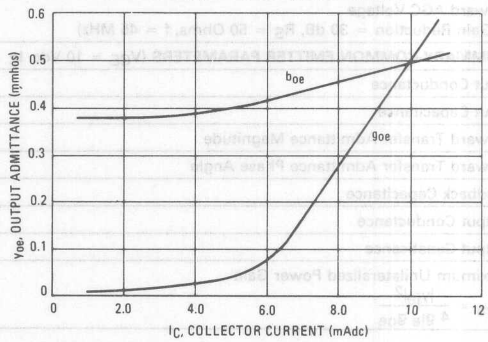
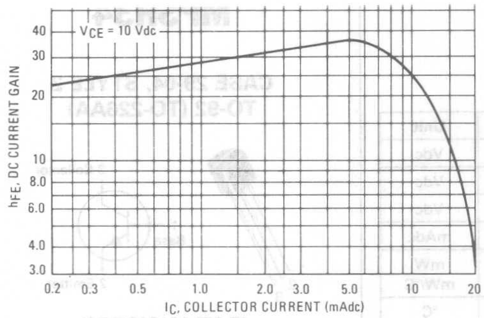


FIGURE 6 – OUTPUT ADMITTANCE





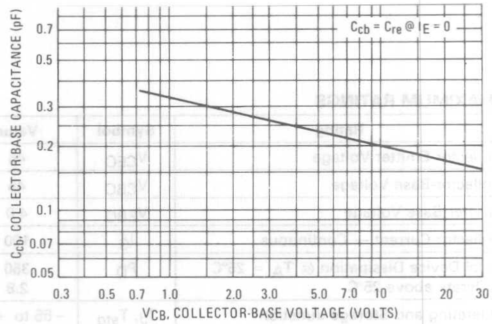


FIGURE 9 – CURRENT-GAIN–BANDWIDTH PRODUCT

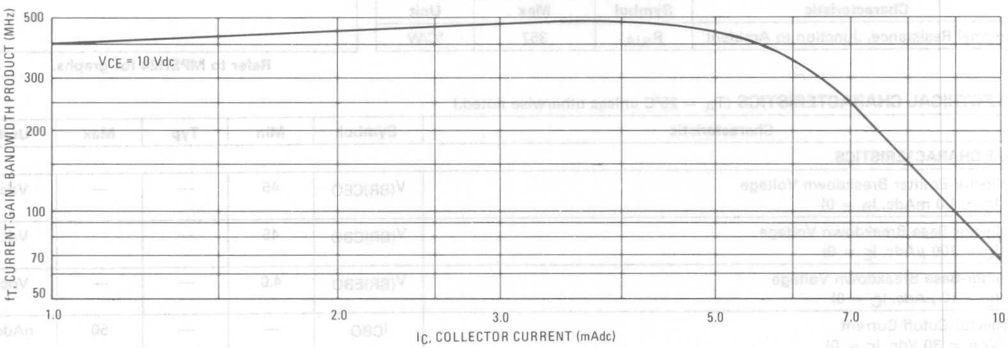
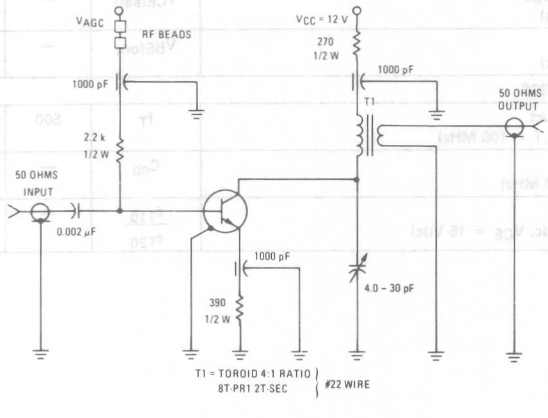


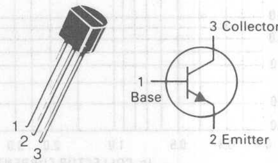
FIGURE 10 – 45 MHz FUNCTIONAL TEST CIRCUIT (UNNEUTRALIZED)



2

MPSH34

CASE 29-04, STYLE 2
TO-92 (TO-226AA)



IF TRANSISTOR

NPN SILICON

Refer to MPSH24 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	45	Vdc
Collector-Base Voltage	V_{CBO}	45	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	100	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	350 2.8	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +135	°C

THERMAL CHARACTERISTICS

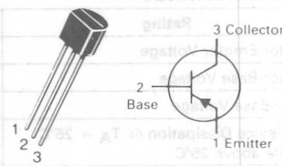
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	45	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	45	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 7.0$ mAdc, $V_{CE} = 15$ Vdc) ($I_C = 20$ mAdc, $V_{CE} = 2.0$ Vdc)	h_{FE}	 40 15	 — —	 — —	—
Collector-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)	$V_{CE(sat)}$	—	—	0.5	Vdc
Base-Emitter On Voltage ($I_C = 7.0$ mAdc, $V_{CE} = 15$ Vdc)	$V_{BE(on)}$	—	—	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 15$ mAdc, $V_{CE} = 15$ Vdc, f = 100 MHz)	f_T	500	720	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{cb}	—	0.25	0.32	pF
Current-Gain — Bandwidth Ratio ($I_C = 15$ mAdc to $I_C = 20$ mAdc, $V_{CE} = 15$ Vdc)	$\frac{f_{T15}}{f_{T20}}$	—	—	1.6	—

MPSH54
MPSH55

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

PNP SILICON

2

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	80	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	100	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

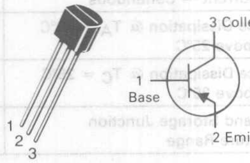
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	200	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	80	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	80	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 60$ Vdc, $I_E = 0$)	I_{CBO}	—	—	50	nAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 1.5$ mAdc, $V_{CE} = 10$ Vdc) MPSH54 MPSH55	h_{FE}	 30 30	 — —	 120 150	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	—	0.25	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 1.5$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	80	—	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, f = 1.0 MHz)	C_{cb}	—	—	1.6	pF
Output Admittance ($I_C = 1.5$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{oe}	—	—	15	μmhos
Noise Figure ($I_C = 1.5$ mAdc, $V_{CE} = 10$ Vdc, $R_S = 50$ ohms, f = 1.0 MHz) MPSH54	NF	—	—	2.0	dB

CASE 29-04, STYLE 2
TO-92 (TO-226AA)



RF AMPLIFIER TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	20	Vdc
Collector-Base Voltage	V_{CBO}	20	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	350 2.81	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	20	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	20	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 10$ Vdc, $I_E = 0$)	I_{CBO}	—	—	100	nAdc
Emitter Cutoff Current ($V_{BE} = 2.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	60	—	—	
Collector-Emitter Saturation Voltage ($I_C = 5.0$ mAdc, $I_B = 0.5$ mAdc)	$V_{CE(sat)}$	—	—	0.5	Vdc
Base-Emitter On Voltage ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc)	$V_{BE(on)}$	—	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	600	—	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{cb}	—	—	0.85	pF
Collector-Emitter Capacitance ($I_B = 0$, $V_{CB} = 10$ Vdc, f = 1.0 MHz)	C_{ce}	—	—	0.65	pF

FIGURE 1 – INPUT ADMITTANCE

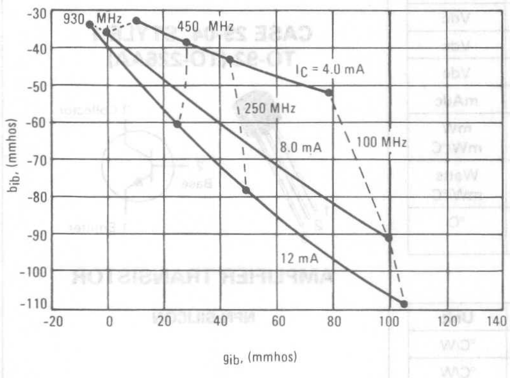


FIGURE 2 – REVERSE TRANSFER ADMITTANCE

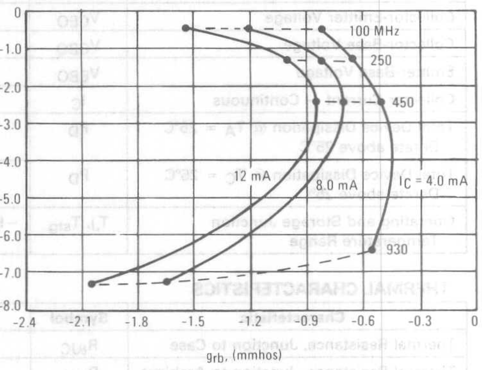


FIGURE 3 – FORWARD TRANSFER ADMITTANCE

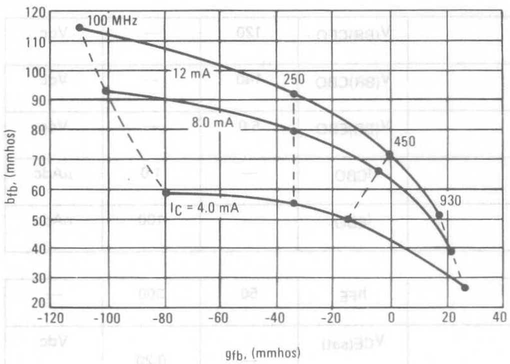


FIGURE 4 – OUTPUT ADMITTANCE

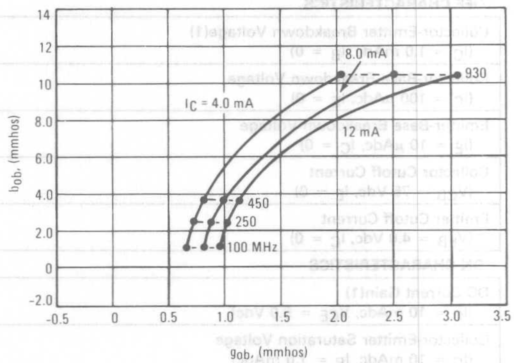
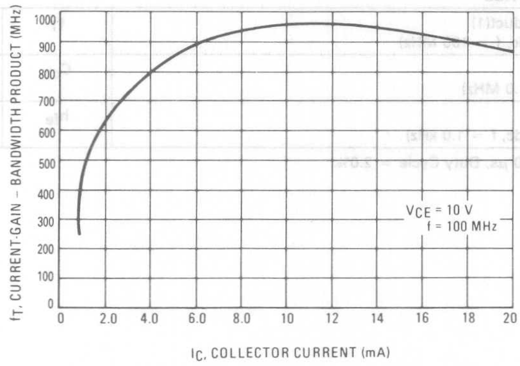
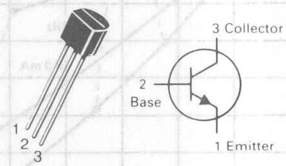


FIGURE 5 – CURRENT-GAIN – BANDWIDTH PRODUCT



MPSL01

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N5550 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	120	Vdc
Collector-Base Voltage	V_{CBO}	140	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	150	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

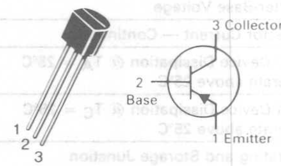
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	120	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	140	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 75$ Vdc, $I_E = 0$)	I_{CBO}	—	1.0	μAdc
Emitter Cutoff Current ($V_{EB} = 4.0$ Vdc, $I_C = 0$)	I_{EBO}	—	100	nAdc
ON CHARACTERISTICS				
DC Current Gain(1) ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc)	h_{FE}	50	300	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)	$V_{CE(sat)}$	 — —	 0.20 0.30	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)(1)	$V_{BE(sat)}$	 — —	 1.2 1.4	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product(1) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	60	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{cb}	—	8.0	pF
Small-Signal Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	30	—	—

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

2

MPSL51

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



AMPLIFIER TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	100	Vdc
Collector-Base Voltage	V_{CBO}	100	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	600	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12.0	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

Refer to 2N5400 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

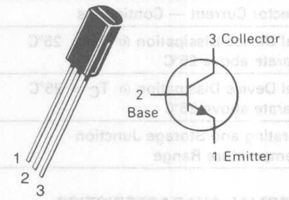
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	100	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	100	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$)	I_{CBO}	—	1.0	μAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	100	nAdc
ON CHARACTERISTICS(1)				
DC Current Gain(1) ($I_C = 50$ mAdc, $V_{CE} = 5.0$ Vdc)	h_{FE}	40	250	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)	$V_{CE(sat)}$	 — —	 0.25 0.30	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)	$V_{BE(sat)}$	 — —	 1.2 1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	60	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{obo}	—	8.0	pF
Small-Signal Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	20	—	—

(1) Pulse Test: Pulse Test = 300 μs, Duty Cycle = 2.0%.

2

MPSW01
MPSW01A

CASE 29-03, STYLE 1
TO-92 (TO-226AE)



HIGH CURRENT TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage MPSW01 MPSW01A	V_{CEO}	30 40	Vdc
Collector-Base Voltage MPSW01 MPSW01A	V_{CBO}	40 50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	1000	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 20	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	MPSW01 MPSW01A	$V_{(BR)CEO}$	30 40	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	MPSW01 MPSW01A	$V_{(BR)CBO}$	40 50	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$) ($V_{CB} = 40$ Vdc, $I_E = 0$)	MPSW01 MPSW01A	I_{CBO}	— —	0.1 0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)		I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1000$ mAdc, $V_{CE} = 1.0$ Vdc)		h_{FE}	55 60 50	— — —	—
Collector-Emitter Saturation Voltage ($I_C = 1000$ mAdc, $I_B = 100$ mAdc)		$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter On Voltage ($I_C = 1000$ mAdc, $V_{CE} = 1.0$ Vdc)		$V_{BE(on)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)		f_T	50	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{obo}	—	20	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — DC CURRENT GAIN

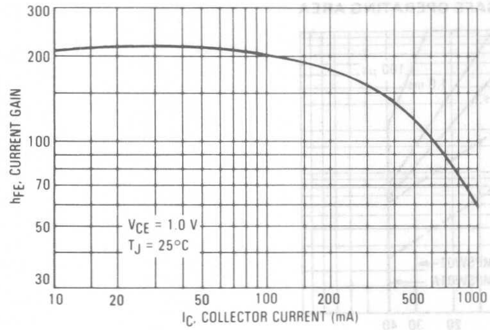


FIGURE 2 — COLLECTOR SATURATION REGION

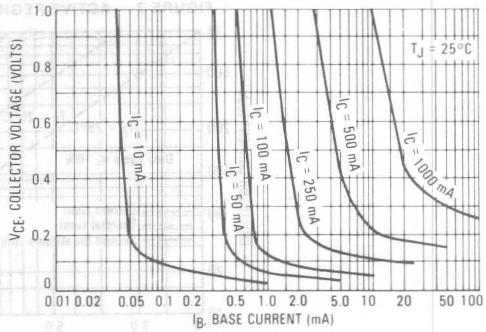


FIGURE 3 — ON VOLTAGES

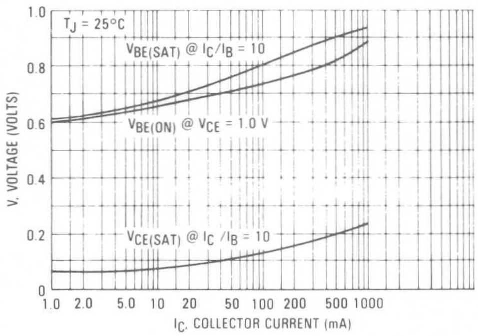


FIGURE 4 — TEMPERATURE COEFFICIENT

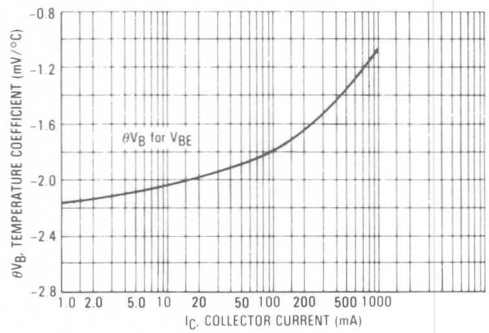


FIGURE 5 — CURRENT GAIN-BANDWIDTH PRODUCT

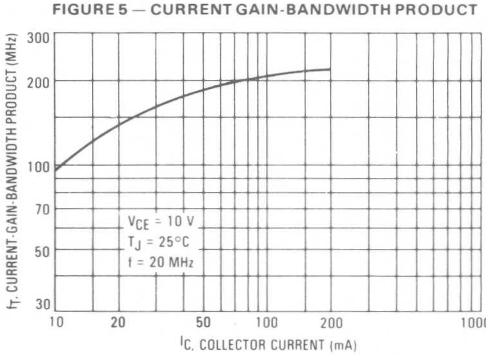


FIGURE 6 — CAPACITANCE

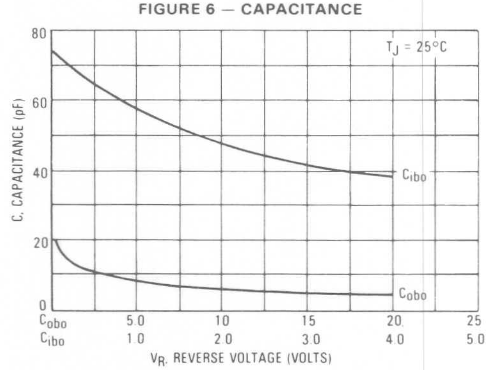
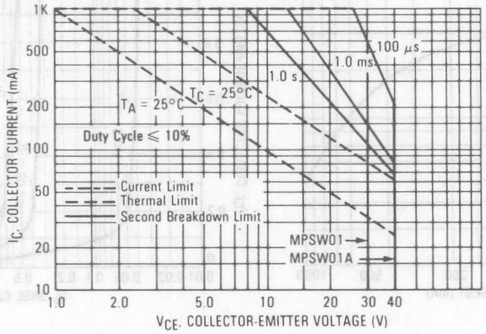
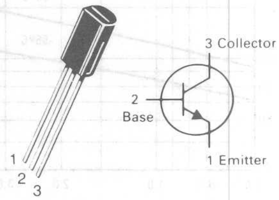


FIGURE 7 — ACTIVE REGION-SAFE OPERATING AREA



MPSW05
MPSW06

CASE 29-03, STYLE 1
TO-92 (TO-226AE)



AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	MPSW05	MPSW06	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	Vdc
Collector-Base Voltage	V_{CBO}	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	4.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 8.0		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 20		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	 MPSW05 MPSW06	$V_{(BR)CEO}$	 60 80	 — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 40$ Vdc, $I_B = 0$) ($V_{CE} = 60$ Vdc, $I_B = 0$)	 MPSW05 MPSW06	I_{CEO}	 — —	 0.5 0.5	μAdc
Collector Cutoff Current ($V_{CB} = 40$ Vdc, $I_E = 0$) ($V_{CB} = 60$ Vdc, $I_E = 0$)	 MPSW05 MPSW06	I_{CBO}	 — —	 0.1 0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)		I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 250$ mAdc, $V_{CE} = 1.0$ Vdc)		h_{FE}	 80 60	 — —	—
Collector-Emitter Saturation Voltage ($I_C = 250$ mAdc, $I_B = 10$ mAdc)		$V_{CE(sat)}$	—	0.40	Vdc
Base-Emitter Saturation Voltage ($I_C = 250$ mAdc, $V_{CE} = 5.0$ Vdc)		$V_{BE(sat)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 200$ mAdc, $V_{CE} = 5.0$ Vdc, f = 20 MHz)		f_T	50	—	MHz
Output Capacitance ($V_{CB} = 10$ V, f = 1.0 MHz)		C_{obo}	—	12	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — D.C. CURRENT GAIN

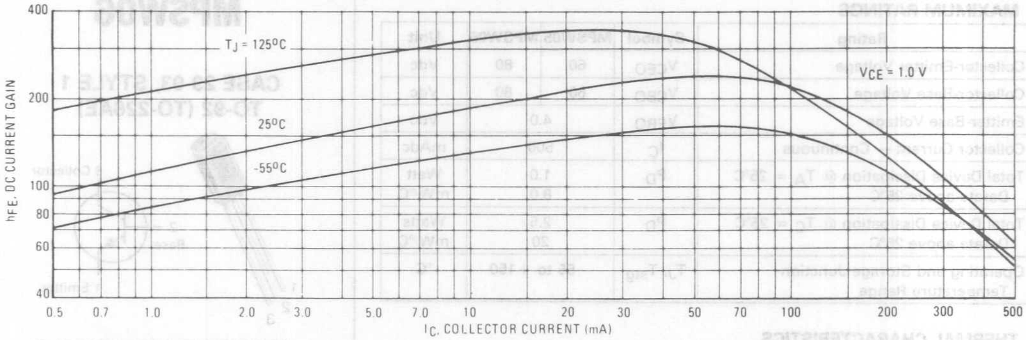


FIGURE 2 — COLLECTOR SATURATION REGION

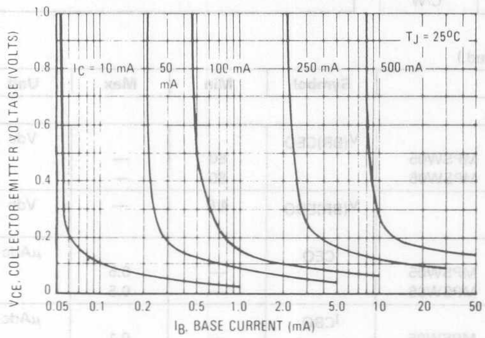


FIGURE 3 — ON VOLTAGES

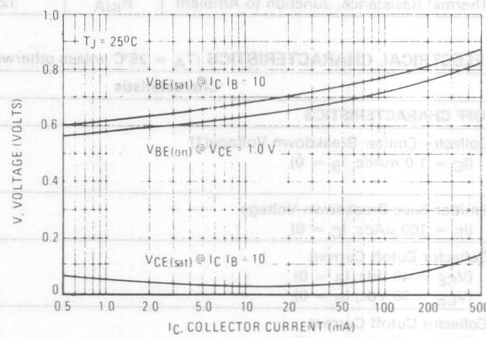


FIGURE 4 — BASE-EMITTER TEMPERATURE COEFFICIENT

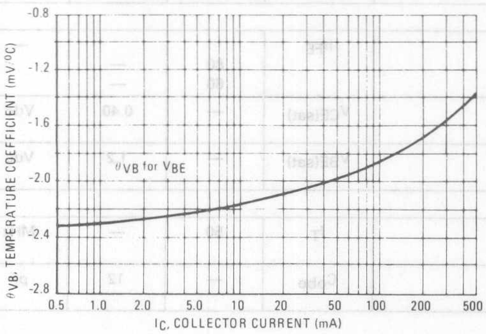


FIGURE 5 — CAPACITANCE

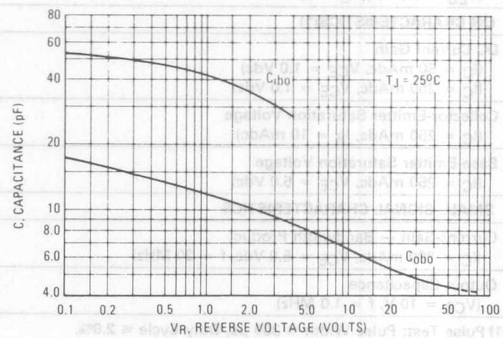


FIGURE 6 — CURRENT GAIN - BANDWIDTH PRODUCT

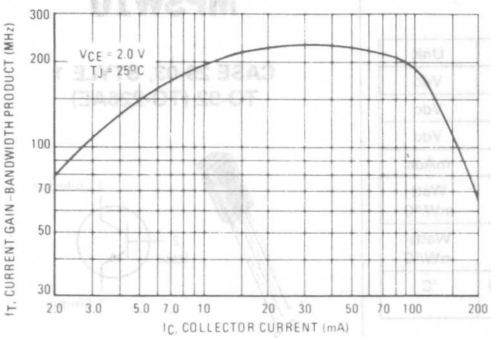
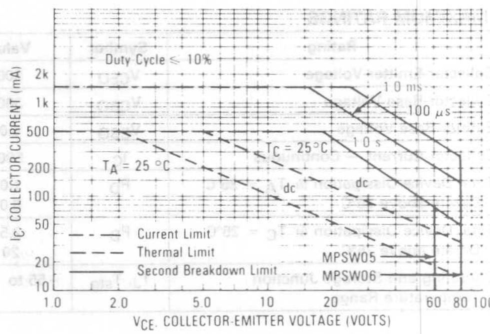
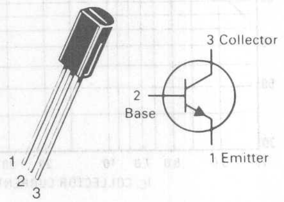


FIGURE 7 — ACTIVE REGION - SAFE OPERATING AREA



MPSW10

CASE 29-03, STYLE 1
TO-92 (TO-226AE)



HIGH VOLTAGE TRANSISTOR

NPN SILICON

Refer to MPSW42 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	300	Vdc
Collector-Base Voltage	V_{CBO}	300	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	500	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	2.5 20	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

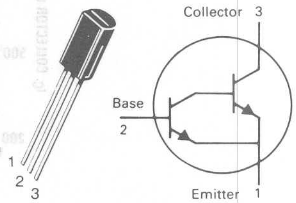
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	300	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	300	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current (V_{CB} = 200 Vdc, I_E = 0)	I_{CBO}	—	0.2	μAdc
Emitter Cutoff Current (V_{EB} = 6.0 Vdc, I_C = 0)	I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS(1)				
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc) (I_C = 30 mAdc, V_{CE} = 10 Vdc)	h_{FE}	 25 40 40	 — — —	—
Collector-Emitter Saturation Voltage (I_C = 30 mAdc, I_B = 3.0 mAdc)	$V_{CE(sat)}$	—	0.75	Vdc
Base-Emitter On Voltage (I_C = 30 mAdc, V_{CE} = 10 Vdc)	$V_{BE(on)}$	—	0.85	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 20 MHz)	f_T	45	—	MHz
Collector-Base Capacitance (V_{CB} = 20 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	—	3.0	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MPSW13
MPSW14

CASE 29-03, STYLE 1
TO-92 (TO-226AE)



DARLINGTON TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CES}	30	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	10	Vdc
Collector Current — Continuous	I_C	1.0	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 20	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 100\ \mu Adc$, $V_{BE} = 0$)		$V_{(BR)CES}$	30	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)		I_{CBO}	—	100	nAdc
Emitter Cutoff Current ($V_{EB} = 10$ Vdc, $I_C = 0$)		I_{EBO}	—	100	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc)	MPSW13 MPSW14	h_{FE}	5000 10,000	— —	—
($I_C = 100$ mAdc, $V_{CE} = 5.0$ Vdc)	MPSW13 MPSW14		10,000 20,000	— —	
Collector-Emitter Saturation Voltage ($I_C = 100$ mAdc, $I_B = 0.1$ mAdc)		$V_{CE(sat)}$	—	1.5	Vdc
Base-Emitter On Voltage ($I_C = 100$ mAdc, $V_{CE} = 5.0$ Vdc)		$V_{BE(on)}$	—	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc, f = 100 MHz)		f_T	125	—	MHz

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) $f_T = |h_{fe}| \cdot f_{test}$.

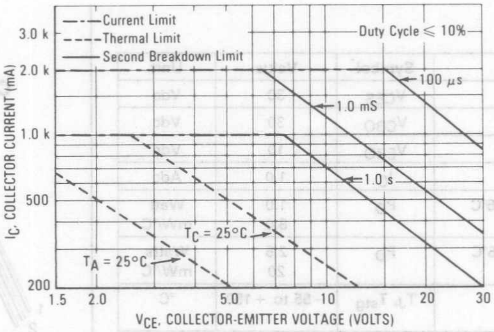


FIGURE 2 — DC CURRENT GAIN

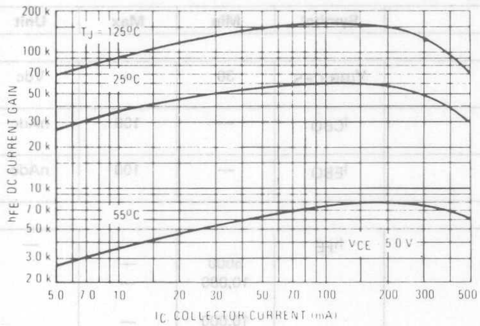


FIGURE 3 — COLLECTOR-SATURATION REGION

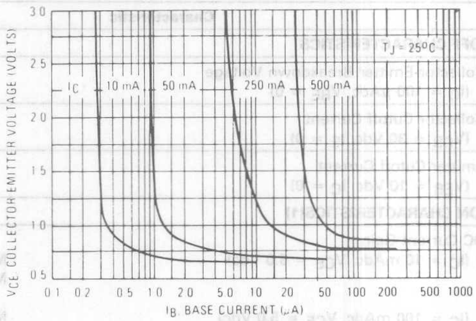


FIGURE 4 — ON VOLTAGES

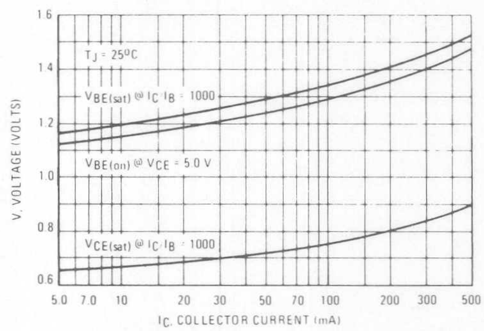


FIGURE 5 — TEMPERATURE COEFFICIENTS

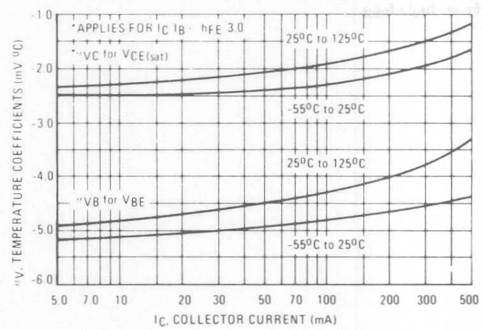


FIGURE 6 — HIGH FREQUENCY CURRENT GAIN

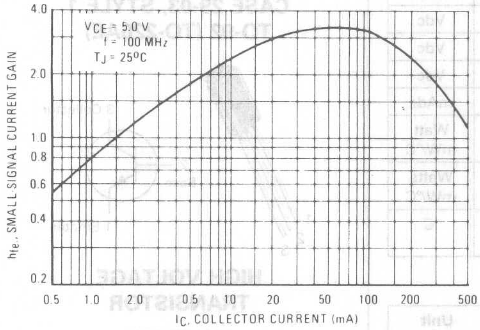
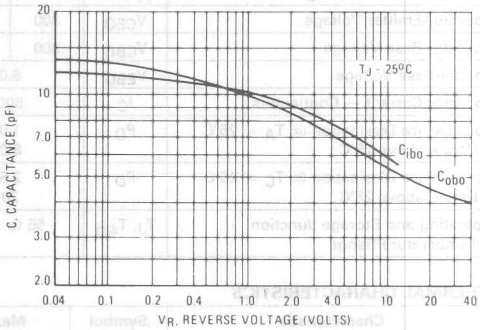


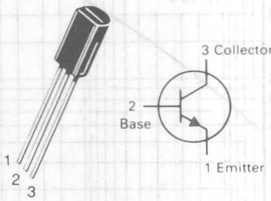
FIGURE 7 — CAPACITANCE



2

MPSW42
MPSW43

CASE 29-03, STYLE 1
TO-92 (TO-226AE)



HIGH VOLTAGE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	MPSW42	MPSW43	Unit
Collector-Emitter Voltage	V_{CEO}	300	200	Vdc
Collector-Base Voltage	V_{CBO}	300	200	Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 8.0		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 20		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	 MPSW42 MPSW43	$V_{(BR)CEO}$	 300 200	 — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	 MPSW42 MPSW43	$V_{(BR)CBO}$	 300 200	 — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 200$ Vdc, $I_E = 0$) ($V_{CB} = 160$ Vdc, $I_E = 0$)	 MPSW42 MPSW43	I_{CBO}	 — —	 0.1 0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 6.0$ Vdc, $I_C = 0$) ($V_{EB} = 4.0$ Vdc, $I_C = 0$)	 MPSW42 MPSW43	I_{EBO}	 — —	 0.1 0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 30$ mAdc, $V_{CE} = 10$ Vdc)	 Both Types Both Types MPSW42 MPSW43	h_{FE}	 25 40 40 40	 — — — —	—
Collector-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)	 MPSW42 MPSW43	$V_{CE(sat)}$	 — —	 0.5 0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)		$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 20 MHz)		f_T	50	—	MHz
Collector-Base Capacitance ($V_{CB} = 20$ Vdc, $I_E = 0$, f = 1.0 MHz)	 MPSW42 MPSW43	C_{cb}	 — —	 3.0 4.0	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — D.C. CURRENT GAIN

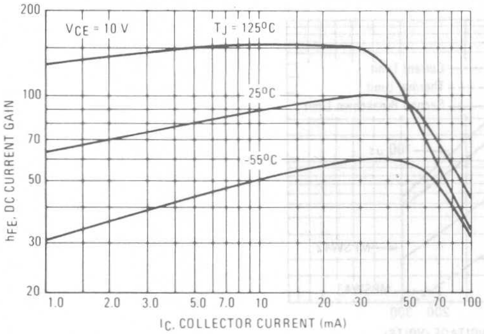


FIGURE 2 — COLLECTOR SATURATION REGION

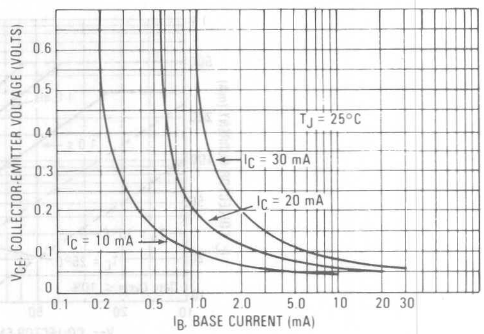


FIGURE 3 — ON VOLTAGES

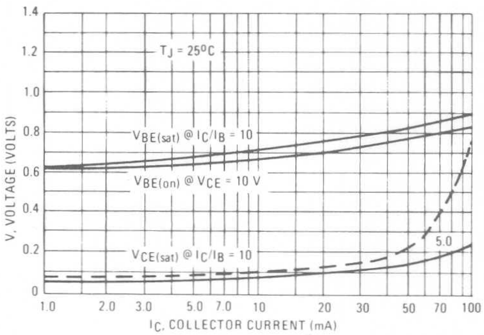


FIGURE 4 — TEMPERATURE COEFFICIENTS

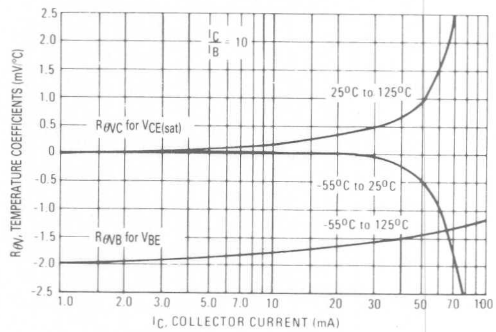


FIGURE 5 — CAPACITANCE

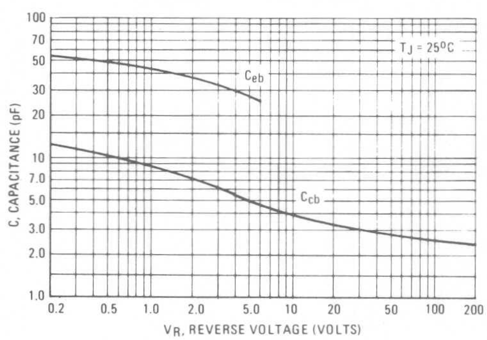
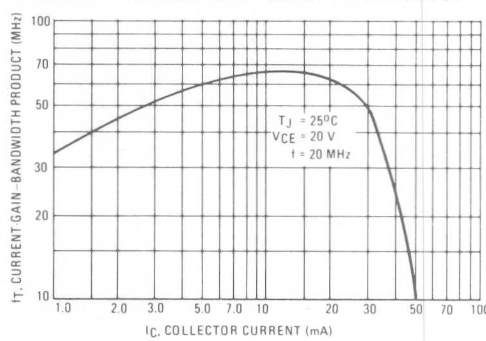
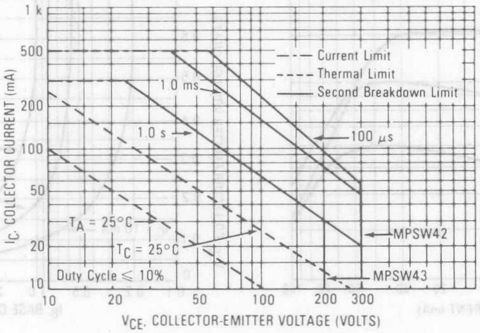


FIGURE 6 — CURRENT GAIN - BANDWIDTH PRODUCT

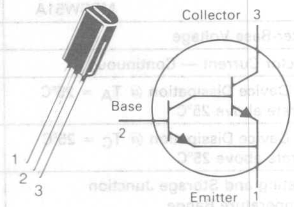


2


1 k
500
200
100
50
20
10
10
20
50
100
200
300
I_C, COLLECTOR CURRENT (mA)
V_{CE}, COLLECTOR-EMITTER VOLTAGE (VOLTS)
Current Limit
Thermal Limit
Second Breakdown Limit
1.0 ms
1.0 s
100 µs
$T_A = 25°C$
$T_C = 25°C$
MPSW42
MPSW43
Duty Cycle ≤ 10%

MPSW45

CASE 29-03, STYLE 1
TO-92 (TO-226AE)



DARLINGTON TRANSISTOR

NPN SILICON

Refer to 2N6426 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CES}	40	Vdc
Collector-Base Voltage	V_{CBO}	50	Vdc
Emitter-Base Voltage	V_{EBO}	12	Vdc
Collector Current — Continuous	I_C	1.0	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 20	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

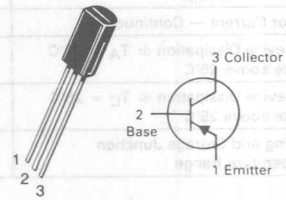
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 100\ \mu Adc$, $V_{BE} = 0$)	$V_{(BR)CES}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu Adc$, $I_E = 0$)	$V_{(BR)CBO}$	50	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu Adc$, $I_C = 0$)	$V_{(BR)EBO}$	12	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	100	nAdc
Emitter Cutoff Current ($V_{EB} = 10$ Vdc, $I_C = 0$)	I_{EBO}	—	100	nAdc
ON CHARACTERISTICS(1)				
DC Current Gain ($I_C = 200$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 500$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 1.0$ Adc, $V_{CE} = 5.0$ Vdc)	h_{FE}	 25,000 15,000 4,000	 150,000 — —	—
Collector-Emitter Saturation Voltage ($I_C = 1.0$ Adc, $I_B = 2.0$ mAdc)	$V_{CE(sat)}$	—	1.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 1.0$ Adc, $I_B = 2.0$ mAdc)	$V_{BE(sat)}$	—	2.0	Vdc
Base-Emitter On Voltage ($I_C = 1.0$ Adc, $V_{CE} = 5.0$ Vdc)	$V_{BE(on)}$	—	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 200$ mAdc, $V_{CE} = 5.0$ Vdc, f = 100 MHz)	f_T	100	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{cb}	—	6.0	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MPSW51
MPSW51A

CASE 29-03, STYLE 1
TO-92 (TO-226AE)



HIGH CURRENT TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage MPSW51 / MPSW51A	V_{CEO}	30 / 40	Vdc
Collector-Base Voltage MPSW51 / MPSW51A	V_{CBO}	40 / 50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	1000	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 / 8.0	Watt / mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 / 20	Watts / mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	MPSW51 / MPSW51A	$V_{(BR)CEO}$	30 / 40	— / —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	MPSW51 / MPSW51A	$V_{(BR)CBO}$	40 / 50	— / —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$) ($V_{CB} = 40$ Vdc, $I_E = 0$)	MPSW51 / MPSW51A	I_{CBO}	— / —	0.1 / 0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)		I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1000$ mAdc, $V_{CE} = 1.0$ Vdc)		h_{FE}	55 / 60 / 50	— / — / —	—
Collector-Emitter Saturation Voltage ($I_C = 1000$ mAdc, $I_B = 100$ mAdc)		$V_{CE(sat)}$	—	0.7	Vdc
Base-Emitter On Voltage ($I_C = 1000$ mAdc, $V_{CE} = 1.0$ Vdc)		$V_{BE(on)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)		f_T	50	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{obo}	—	30	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — DC CURRENT GAIN

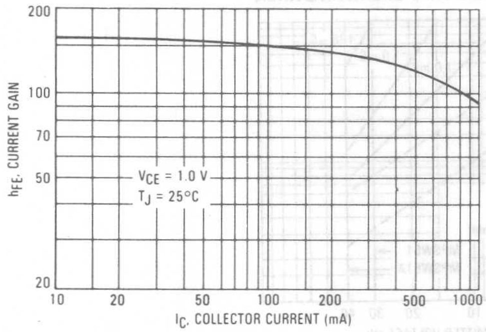


FIGURE 2 — COLLECTOR SATURATION REGION

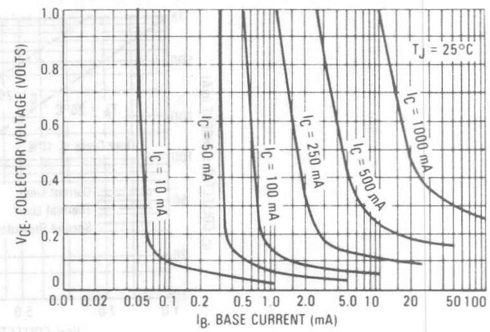


FIGURE 3 — ON VOLTAGES

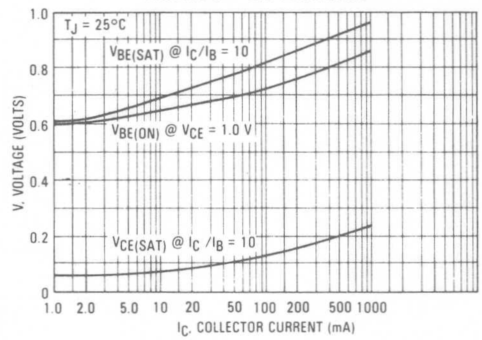


FIGURE 4 — TEMPERATURE COEFFICIENT

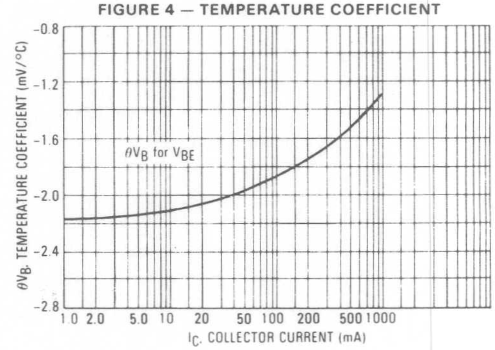


FIGURE 5 — CURRENT GAIN-BANDWIDTH PRODUCT

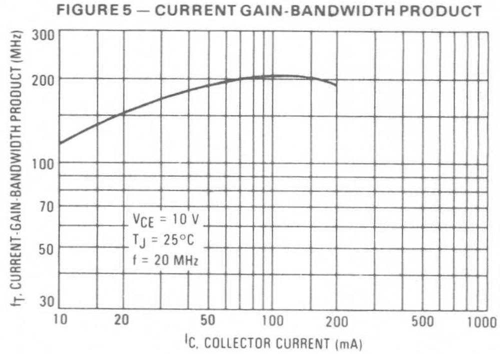


FIGURE 6 — CAPACITANCE

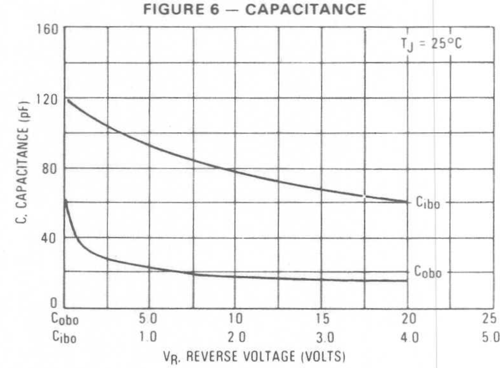
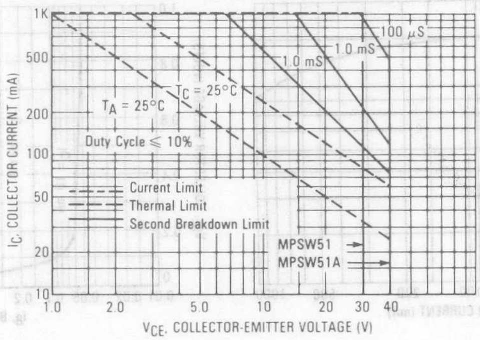
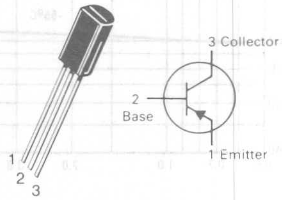


FIGURE 7 — ACTIVE REGION-SAFE OPERATING AREA



MPSW55
MPSW56

CASE 29-03, STYLE 1
TO-92 (TO-226AE)



AMPLIFIER TRANSISTOR

PNP SILICON

2

MAXIMUM RATINGS

Rating	Symbol	MPSW55	MPSW56	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	Vdc
Collector-Base Voltage	V_{CBO}	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	4.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 8.0		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 20		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	 MPSW55 MPSW56	$V_{(BR)CEO}$	 60 80	 — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 40$ Vdc, $I_B = 0$) ($V_{CE} = 60$ Vdc, $I_B = 0$)	 MPSW55 MPSW56	I_{CEO}	 — —	 0.5 0.5	μAdc
Collector Cutoff Current ($V_{CB} = 40$ Vdc, $I_E = 0$) ($V_{CB} = 60$ Vdc, $I_E = 0$)	 MPSW55 MPSW56	I_{CBO}	 — —	 0.1 0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)		I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 250$ mAdc, $V_{CE} = 1.0$ Vdc)		h_{FE}	 80 50	 — —	—
Collector-Emitter Saturation Voltage ($I_C = 250$ mAdc, $I_B = 10$ mAdc)		$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter On Voltage ($I_C = 250$ mAdc, $V_{CE} = 5.0$ Vdc)		$V_{BE(on)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 250$ mAdc, $V_{CE} = 5.0$ Vdc, f = 100 MHz)		f_T	50	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, f = 1.0 MHz)		C_{obo}	—	15	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — D.C. CURRENT GAIN

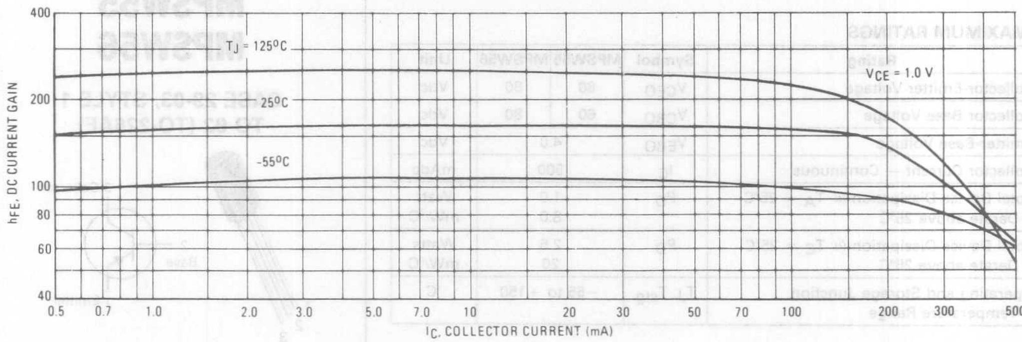


FIGURE 2 — COLLECTOR SATURATION REGION

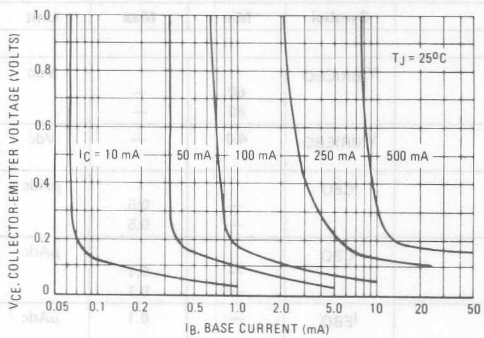


FIGURE 3 — ON VOLTAGES

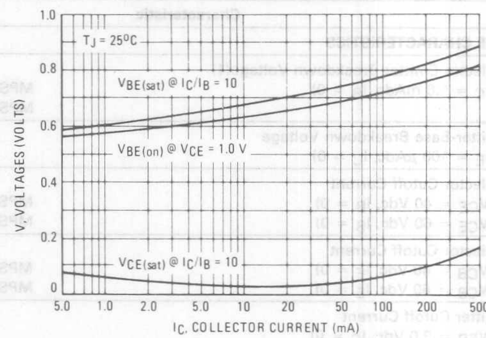


FIGURE 4 — BASE-EMITTER TEMPERATURE COEFFICIENT

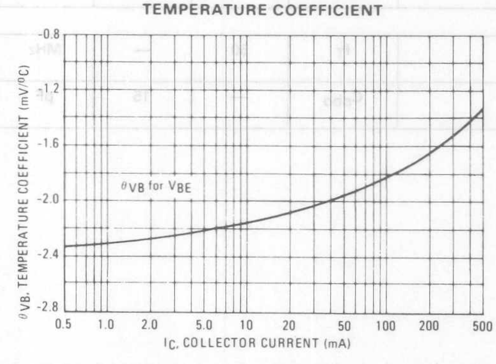


FIGURE 5 — CAPACITANCE

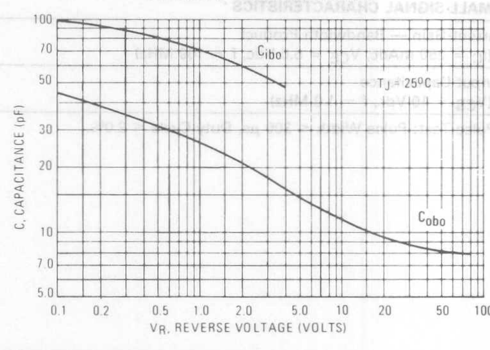


FIGURE 6 — CURRENT GAIN - BANDWIDTH PRODUCT

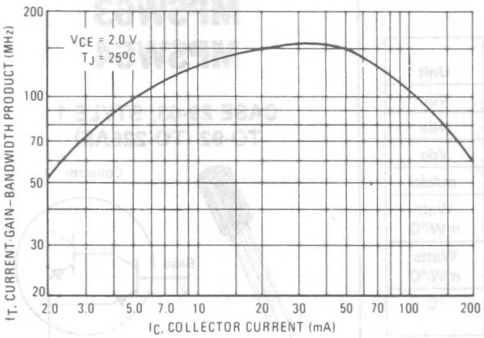
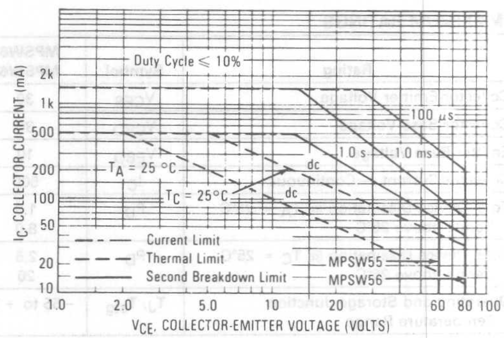
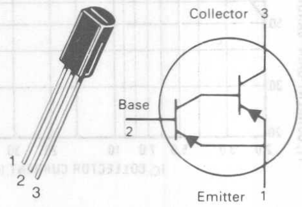


FIGURE 7 — ACTIVE REGION - SAFE OPERATING AREA



MPSW64

CASE 29-03, STYLE 1
TO-92 (TO-226AE)



DARLINGTON TRANSISTOR

PNP SILICON

Rating	Symbol	MPSW63 MPSW64	Unit
Collector-Emitter Voltage	V_{CES}	30	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	10	Vdc
Collector Current — Continuous	I_C	500	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 20	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 100\ \mu Adc, V_{BE} = 0$)		$V_{(BR)CES}$	30	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)		I_{CBO}	—	100	nAdc
Emitter Cutoff Current ($V_{EB} = 10$ Vdc, $I_C = 0$)		I_{EBO}	—	100	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 5.0$ Vdc)	 MPSW63 MPSW64 MPSW63 MPSW64	h_{FE}	 5,000 10,000 10,000 20,000	 — — — —	—
Collector-Emitter Saturation Voltage ($I_C = 100$ mAdc, $I_B = 0.1$ mAdc)		$V_{CE(sat)}$	—	1.5	Vdc
Base-Emitter On Voltage ($I_C = 100$ mAdc, $V_{CE} = 5.0$ Vdc)		$V_{BE(on)}$	—	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc, f = 100 MHz)		f_T	125	—	MHz

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) $f_T = |h_{fe}| \cdot f_{test}$.

FIGURE 1 – DC CURRENT GAIN

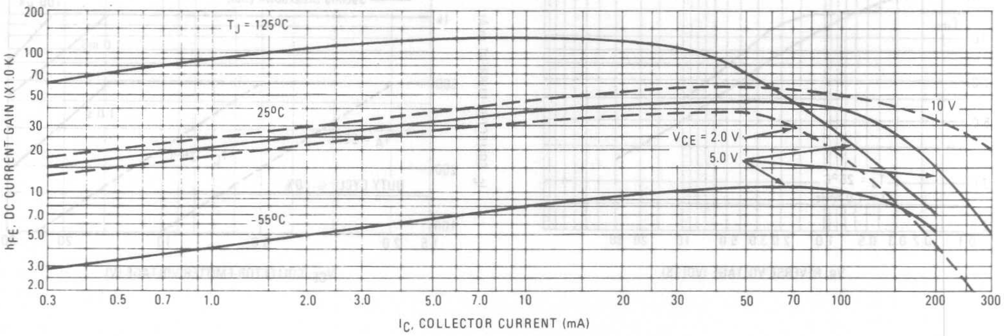


FIGURE 2 – "ON" VOLTAGE

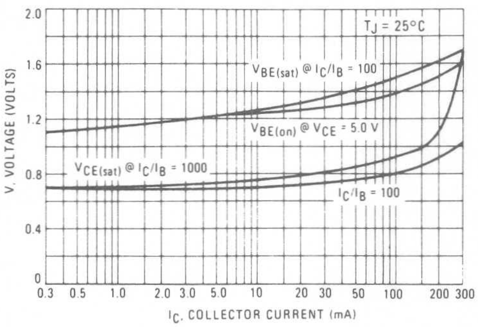


FIGURE 3 – COLLECTOR SATURATION REGION

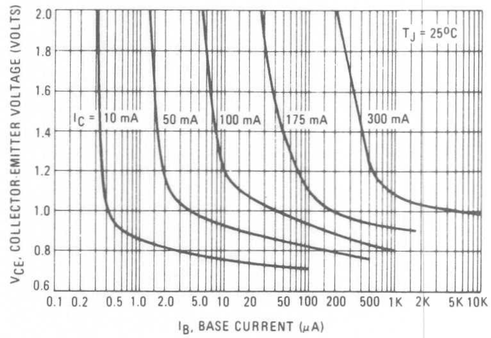


FIGURE 4 – TEMPERATURE COEFFICIENTS

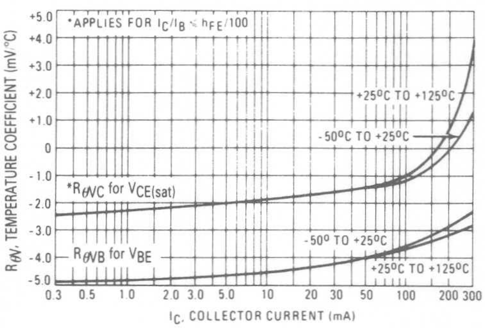
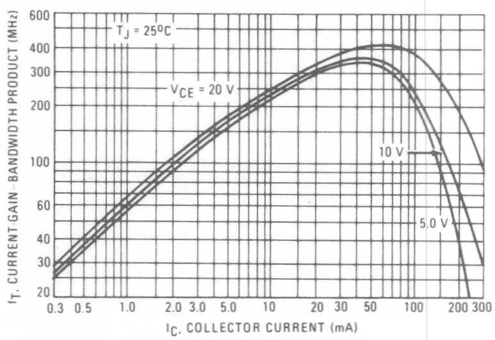


FIGURE 5 – CURRENT-GAIN–BANDWIDTH PRODUCT



2

FIGURE 6 — CAPACITANCE

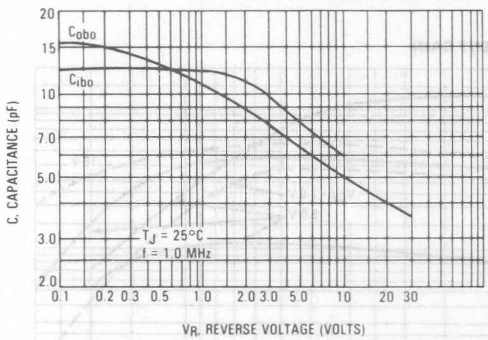
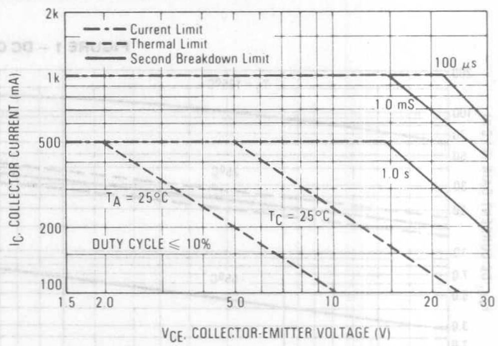
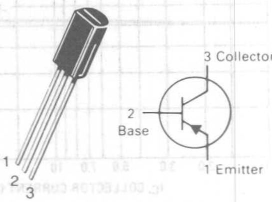


FIGURE 7 — ACTIVE REGION, SAFE OPERATING AREA



MPSW92
MPSW93

CASE 29-03, STYLE 1
TO-92 (TO-226AE)



HIGH VOLTAGE TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	MPSW92	MPSW93	Unit
Collector-Emitter Voltage	V_{CEO}	300	200	Vdc
Collector-Base Voltage	V_{CBO}	300	200	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.0 8.0		Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	2.5 20		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)	MPSW92 MPSW93	$V_{(BR)CEO}$	300 200	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	MPSW92 MPSW93	$V_{(BR)CBO}$	300 200	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 200 Vdc, I_E = 0) (V_{CB} = 160 Vdc, I_E = 0)	MPSW92 MPSW93	I_{CBO}	— —	0.25 0.25	μAdc
Emitter Cutoff Current (V_{EB} = 3.0 Vdc, I_C = 0)		I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc) (I_C = 30 mAdc, V_{CE} = 10 Vdc)	Both Types Both Types MPSW92 MPSW93	h_{FE}	25 40 25 25	— — — —	—
Collector-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)	MPSW92 MPSW93	$V_{CE(sat)}$	— —	0.5 0.5	Vdc
Base-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)		$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 20 MHz)		f_T	50	—	MHz
Collector-Base Capacitance (V_{CB} = 20 Vdc, I_E = 0, f = 1.0 MHz)	MPSW92 MPSW93	C_{cb}	— —	6.0 8.0	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — D.C. CURRENT GAIN

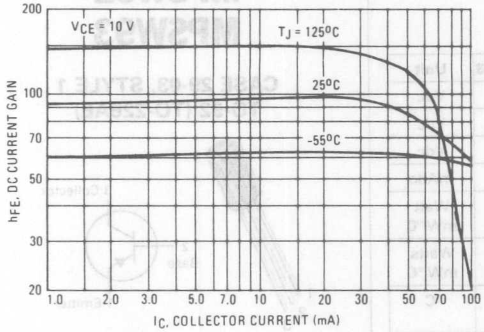


FIGURE 2 — COLLECTOR SATURATION REGION

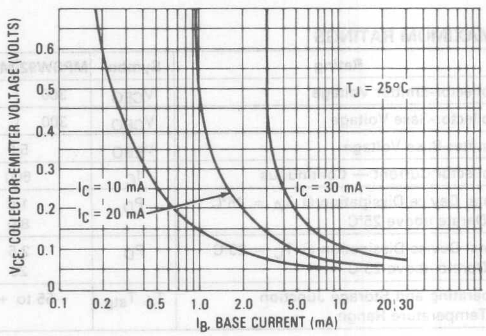


FIGURE 3 — ON VOLTAGES

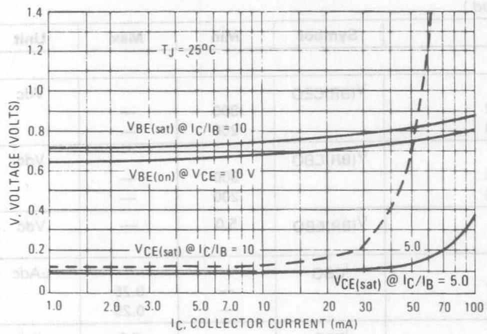


FIGURE 4 — TEMPERATURE COEFFICIENTS

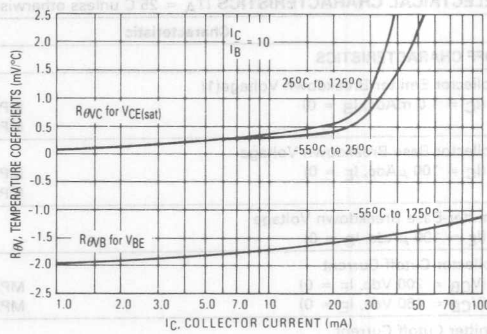


FIGURE 5 — CAPACITANCE

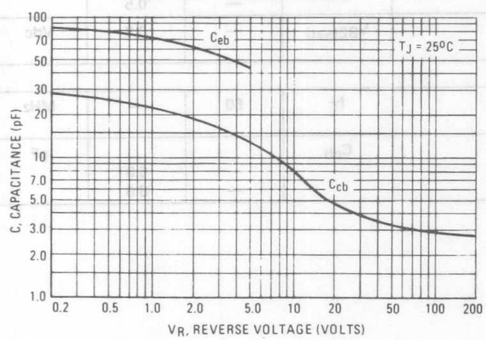


FIGURE 6 — CURRENT GAIN - BANDWIDTH PRODUCT

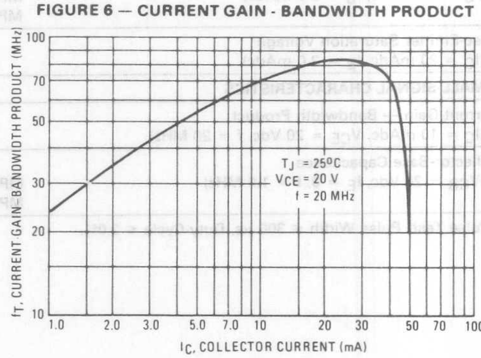
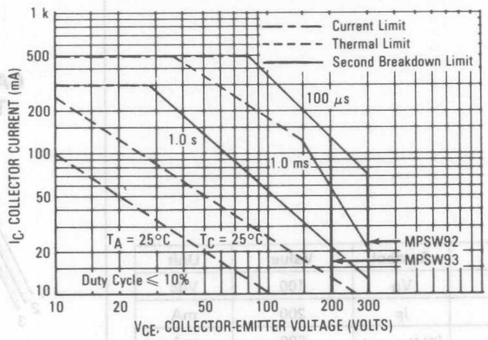


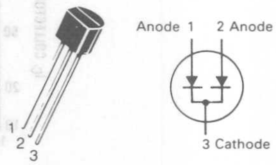
FIGURE 7 — ACTIVE REGION SAFE OPERATING AREA



2

MSD6100

CASE 29-04, STYLE 3
TO-92 (TO-226AA)



DUAL SWITCHING DIODE
COMMON CATHODE

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	100	Vdc
Recurrent Peak Forward Current	I_F	200	mA
Peak Forward Surge Current (Pulse Width = 10 μsec)	$I_{FM(surge)}$	500	mA
Power Dissipation @ T_A = 25°C Derate above 25°C	P_D(1)	625 5.0	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}(1)	−55 to +135	°C

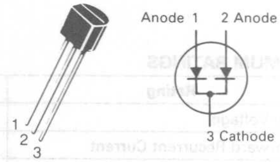
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Breakdown Voltage ($I_{(BR)}$ = 100 μAdc)	$V_{(BR)}$	100	—	Vdc
Reverse Current (V_R = 100 Vdc) (V_R = 50 Vdc) (V_R = 50 Vdc, T_A = 125°C)	I_R	 — — —	 5.0 0.1 20	μAdc
Forward Voltage (I_F = 1.0 mAdc) (I_F = 10 mAdc) (I_F = 100 mAdc)	V_F	 0.55 0.67 0.75	 0.7 0.82 1.1	Vdc
Capacitance (V_R = 0)	C	—	1.5	pF
Reverse Recovery Time (I_F = I_R = 10 mAdc, V_R = 5.0 Vdc, i_{rr} = 1.0 mAdc)	t_{rr}	—	4.0	ns

(1) Continuous package improvements have enhanced these guaranteed Maximum Ratings as follows: P_D = 1.0 W @ T_C = 25°C, Derate above 25°C — 8.0 mW/°C, T_J = −65 to +150°C, θ_{JC} = 125°C/W.

MSD6102

CASE 29-04, STYLE 3
TO-92 (TO-226AA)



DUAL DIODE
COMMON CATHODE

MAXIMUM RATINGS

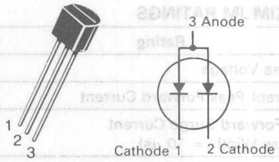
Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	Vdc
Recurrent Peak Forward Current	I_F	200	mA
Peak Forward Surge Current (Pulse Width = 10 μs)	$I_{FM(surge)}$	500	mA
Power Dissipation @ T_A = 25°C Derate above 25°C	P_D(1)	625 5.0	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}(1)	−55 to +135	°C

(1) Continuous package improvements have enhanced these guaranteed Maximum Ratings as follows: P_D = 1.0 W @ T_C = 25°C, Derate above 25°C — 8.0 mW/°C, T_J = −65 to +150°C, θ_{JC} = 125°C/W.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Breakdown Voltage ($I_{(BR)}$ = 100 μAdc)	$V_{(BR)}$	70	—	Vdc
Reverse Current (V_R = 50 Vdc)	I_R	—	0.1	μAdc
Forward Voltage (I_F = 10 mAdc)	V_F	—	1.0	Vdc
Capacitance (V_R = 0)	C	—	3.0	pF
Reverse Recovery Time (I_F = I_R = 10 mAdc, V_R = 5.0 Vdc, i_{rr} = 1.0 mAdc)	t_{rr}	—	100	ns

CASE 29-04, STYLE 4
TO-92 (TO-226AA)



DUAL DIODE
COMMON ANODE

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	Vdc
Peak Forward Recurrent Current	I_F	200	mA
Peak Forward Surge Current (Pulse Width = 10 μs)	$I_{FM(surge)}$	500	mA
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D(1)	625 5.0	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}(1)	−55 to +135	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Breakdown Voltage ($I_{(BR)}$ = 100 μAdc)	$V_{(BR)}$	70	—	—	Vdc
Reverse Current (V_R = 50 Vdc)	I_R	—	—	0.1	μAdc
Forward Voltage (I_F = 10 mAdc)	V_F	—	0.80	1.0	Vdc
Capacitance (V_R = 0)	C	—	5.0	8.0	pF
Reverse Recovery Time (I_F = I_R = 10 mAdc, V_R = 5.0 Vdc, i_{rr} = 1.0 mAdc)	t_{rr}	—	—	100	ns

(1) Continuous package improvements have enhanced these guaranteed Maximum Ratings as follows: P_D = 1.0 W @ T_C = 25°C, Derate above 8.0 mW/°C, P_D = 10 W @ T_C = 25°C, Derate above 80 mW/°C, T_J, T_{stg} = −55 to +150°, θ_{JC} = 12.5°C/W, θ_{JA} = 125°C.

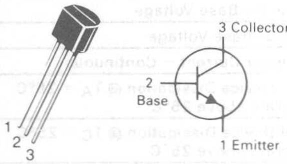
MAXIMUM RATINGS

Rating	Symbol	PBF259,S	Unit
Collector-Emitter Voltage	V_{CEO}	300	Vdc
Collector-Base Voltage	V_{CBO}	300	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous	I_C	500	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



HIGH VOLTAGE TRANSISTORS

NPN SILICON

Refer to MPSA42 for graphs.

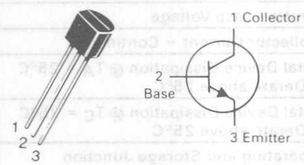
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (1) (I_C = 1.0 mAdc, I_B = 0)		$V_{(BR)CEO}$	300	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	300		Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 250 Vdc, I_E = 0)		I_{CBO}	—	50	nAdc
Emitter Cutoff Current (V_{EB} = 3.0 V)		I_{EBO}	—	20	nAdc
Collector Cutoff Current (V_{CE} = 10 V)		I_{CEO}	—	50	nAdc
ON CHARACTERISTICS (1)					
DC Current Gain (I_C = 20 mAdc, V_{CE} = 10 Vdc) (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 30 mAdc, V_{CE} = 10 Vdc)	 PBF259S All Types All Types	h_{FE}	 60 25 25	 — — —	—
Collector-Emitter Saturation Voltage (I_C = 30 mAdc, I_B = 1.5 mAdc) (I_C = 30 mAdc, I_B = 60 mAdc)		$V_{CE(sat)}$	 — —	 0.5 1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)		f_T	40	—	MHz
Output Capacitance (V_{CB} = 20 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	3.0	pF

2

PBF259R
PBF259RS

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



HIGH VOLTAGE TRANSISTORS

NPN SILICON

Refer to MPSA92 for graphs.

MAXIMUM RATINGS

Rating	Symbol	PBF493R,RS	Unit
Collector-Emitter Voltage	V_{CEO}	300	Vdc
Collector-Base Voltage	V_{CBO}	300	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous	I_C	500	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	°C

THERMAL CHARACTERISTICS

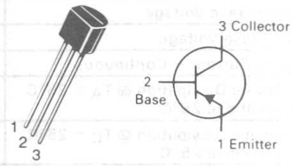
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (1) ($I_C = 3.0$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	300	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)		$V_{(BR)CBO}$	300	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 250$ Vdc, $I_E = 0$)		I_{CBO}	—	50	nAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ V)		I_{EBO}	—	20	nAdc
Collector Cutoff Current ($V_{CE} = 10$ V)		I_{CEO}	—	50	nAdc
ON CHARACTERISTICS (1)					
DC Current Gain ($I_C = 20$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 30$ mAdc, $V_{CE} = 10$ Vdc)	 PBF259RS All Types All Types	h_{FE}	 60 25 25		—
Collector-Emitter Saturation Voltage ($I_C = 30$ mAdc, $I_B = 1.5$ mAdc) ($I_C = 30$ mAdc, $I_B = 60$ mAdc)		$V_{CE(sat)}$	 — —	 0.5 1.0	Vdc
Base-Emitter Saturation Voltage ($I_C = 20$ mA, $I_B = 2.0$ mA)		$V_{BE(sat)}$	—	0.9	V
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)		f_T	40	—	MHz
Output Capacitance ($V_{CB} = 20$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{obo}	—	3.0	pF

PBF493
PBF493S

CASE 29-04, STYLE 1
TO-92 (TO-226AA)



HIGH VOLTAGE TRANSISTORS

PNP SILICON

Refer to MPSA92 for graphs.

2

MAXIMUM RATINGS

Rating	Symbol	PBF493,S	Unit
Collector-Emitter Voltage	V_{CEO}	300	Vdc
Collector-Base Voltage	V_{CBO}	300	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous	I_C	500	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (1) (I_C = 1.0 mAdc, I_B = 0)		$V_{(BR)CEO}$	300	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	300	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 200 Vdc, I_E = 0)		I_{CBO}	—	0.25	μAdc
Emitter Cutoff Current (V_{EB} = 3.0 V)		I_{EBO}	—	20	nAdc
Collector Cutoff Current (V_{CE} = 10 V)		I_{CEO}	—	250	nAdc
ON CHARACTERISTICS (1)					
DC Current Gain (I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc) (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 30 mAdc, V_{CE} = 10 Vdc)	 PBF493S All Types All Types	h_{FE}	 40 40 25	 — — —	—
Collector-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)		$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)		$V_{BE(sat)}$		0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 20 MHz)		f_T	50	—	MHz
Output Capacitance (V_{CB} = 20 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	6.0	pF

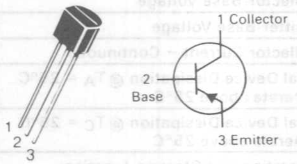
MAXIMUM RATINGS

Rating	Symbol	PBF259R,RS	Unit
Collector-Emitter Voltage	V_{CEO}	300	Vdc
Collector-Base Voltage	V_{CBO}	300	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous	I_C	500	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	200	°C/W

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



HIGH VOLTAGE TRANSISTORS

PNP SILICON

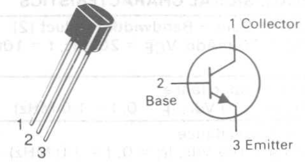
Refer to MPSA42 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (1) ($I_C = 1.0$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	300	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)		$V_{(BR)CBO}$	300	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 200$ Vdc, $I_E = 0$)		I_{CBO}	—	0.25	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ V)		I_{EBO}	—	20	nAdc
Collector Cutoff Current ($V_{CE} = 10$ V)		I_{CEO}	—	250	nAdc
ON CHARACTERISTICS (1)					
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 30$ mAdc, $V_{CE} = 10$ Vdc)	 PBF493RS All Types All Types	h_{FE}	 40 40 25	— — —	—
Collector-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)		$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)		$V_{BE(sat)}$		0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 20 MHz)		f_T	50		MHz
Output Capacitance ($V_{CB} = 20$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{obo}	—	6.0	pF

P2N2222
P2N2222A

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	P2N 2222	P2N 2222A	Unit
Collector-Emitter Voltage	V_{CEO}	30	40	Vdc
Collector-Base Voltage	V_{CBO}	60	75	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	6.0	Vdc
Collector Current – Continuous	I_C	600		mAdc
Total Device Dissipation $T_A = 25°C$ Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation $T_C = 25°C$ Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

Refer to MPS2222 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 10$ mAdc, $I_B = 0$)	 P2N2222 P2N2222A	$V_{(BR)CEO}$	 30 40	 — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	 P2N2222 P2N2222A	$V_{(BR)CBO}$	 60 75	 — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	 P2N2222 P2N2222A	$V_{(BR)EBO}$	 5.0 6.0	 — —	Vdc
Collector Cutoff Current ($V_{CE} = 60$ Vdc, $V_{EB(off)} = 3.0$ Vdc)	 P2N2222A	I_{CEX}	—	10	nAdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$) ($V_{CB} = 60$ Vdc, $I_E = 0$) ($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = 150°C$) ($V_{CB} = 60$ Vdc, $I_E = 0$, $T_A = 150°C$)	 P2N2222 P2N2222A P2N2222 P2N2222A	I_{CBO}	 — — — —	 0.01 0.01 10 10	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)	 P2N2222A	I_{EBO}	—	10	nAdc
Collector Cutoff Current ($V_{CE} = 10$ V)		I_{CEO}	—	10	nAdc
Base Cutoff Current ($V_{CE} = 60$ Vdc, $V_{EB(off)} = 3.0$ Vdc)	 P2N2222A	I_{BEX}	—	20	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, $T_A = -55°C$) ($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc) (1) ($I_C = 150$ mAdc, $V_{CE} = 1.0$ Vdc) (1) ($I_C = 500$ mAdc, $V_{CE} = 10$ Vdc) (1)	 P2N2222A only P2N2222 P2N2222A	h_{FE}	 35 50 75 35 100 50 30 40	 — — — — 300 — — —	—
Collector-Emitter Saturation Voltage (1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	 P2N2222 P2N2222A P2N2222 P2N2222A	$V_{CE(sat)}$	 — — — —	 0.4 0.3 1.6 1.0	Vdc

2

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Base-Emitter Saturation Voltage (1)		$V_{BE(sat)}$			Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)	P2N2222		—	1.3	
	P2N2222A		0.6	1.2	
(I_C = 500 mAdc, I_B = 50 mAdc)	P2N2222		—	2.6	
	P2N2222A		—	2.0	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (2)		f_T			MHz
(I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	P2N2222		250	—	
	P2N2222A		300	—	
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	8.0	pF
Input Capacitance		C_{ibo}			pF
(V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	P2N2222		—	30	
	P2N2222A		—	25	
Input Impedance		h_{ie}			kΩ
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	P2N2222A		2.0	8.0	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	P2N2222A		0.25	1.25	
Voltage Feedback Ratio		h_{re}			$X10^{-4}$
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	P2N2222A			8.0	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	P2N2222A			4.0	
Small-Signal Current Gain		h_{fe}			—
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	P2N2222A		50	300	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	P2N2222A		75	375	
Output Admittance		h_{oe}			μmhos
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	P2N2222A		5.0	35	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	P2N2222A		25	200	
Collector Base Time Constant (I_E = 20 mAdc, V_{CB} = 20 Vdc, f = 31.8 MHz)	P2N2222A	$rb'C_c$	—	150	ps
Noise Figure (I_C = 100 μAdc, V_{CE} = 10 Vdc, R_S = 1.0 kΩ, f = 1.0 kHz)	P2N2222A	N_F		4.0	dB
SWITCHING CHARACTERISTICS MPS2222A only					
Delay Time	(V_{CC} = 30 Vdc, $V_{BE(off)}$ = 0.5 Vdc,	t_d	—	10	ns
Rise Time	I_C = 150 mAdc, I_{B1} = 15 mAdc) (Figure 1)	t_r	—	25	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc,	t_s	—	225	ns
Fall Time	I_{B1} = I_{B2} = 15 mAdc) (Figure 2)	t_f	—	60	ns

(1) Pulse Test: Pulse Width ≦ 300 μs, Duty Cycle ≦ 2.0%. (2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

FIGURE 1 — TURN-ON TIME

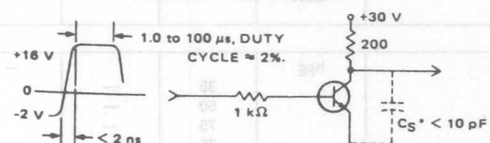
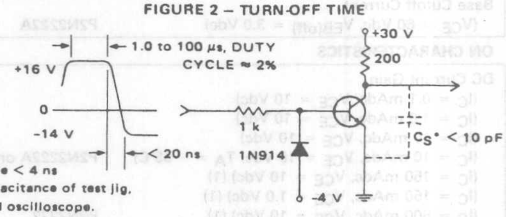


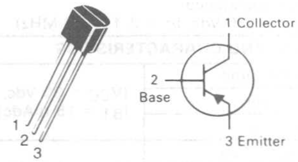
FIGURE 2 — TURN-OFF TIME



Scope Rise Time < 4 ns
*Total shunt capacitance of test jig, connectors, and oscilloscope.

P2N2907
P2N2907A

CASE 29-04, STYLE 17
TO-92 (TO-226AA)



AMPLIFIER TRANSISTORS

PNP SILICON

Refer to MPS2907 for graphs.

MAXIMUM RATINGS

Rating	Symbol	P2N 2907	P2N 2907A	Unit
Collector-Emitter Voltage	V_{CEO}	40	60	Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current − Continuous	I_C	600		mAdc
Total Device Dissipation $T_A = 25°C$ Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation $T_C = 25°C$ Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (1) (I_C = 10 mAdc, I_B = 0)	 P2N2907 P2N2907A	$V_{(BR)CEO}$	 40 60	 — —	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CE} = 30 Vdc, $V_{EB(off)}$ = 0.5 Vdc)		I_{CEX}	—	50	nAdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0) (V_{CB} = 50 Vdc, I_E = 0, T_A = 125°C)	 P2N2907 P2N2907A P2N2907 P2N2907A	I_{CBO}	 — — — —	 0.02 0.01 20 10	μAdc
Emitter Cutoff Current (V_{EB} = 3.0 Vdc)		I_{EBO}	—	10	nAdc
Collector Cutoff Current (V_{CE} = 10 V)		I_{CEO}	—	10	nAdc
Base Cutoff Current (V_{CE} = 30 Vdc, $V_{EB(off)}$ = 0.5 Vdc)		I_{BEX}	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 0.1 mAdc, V_{CE} = 10 Vdc) (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc) (I_C = 150 mAdc, V_{CE} = 10 Vdc) (1) (I_C = 500 mAdc, V_{CE} = 10 Vdc) (1)	 P2N2907 P2N2907A P2N2907 P2N2907A P2N2907 P2N2907A P2N2907, P2N2907A P2N2907 P2N2907A	h_{FE}	 35 75 50 100 75 100 100 30 50	 — — — — — — 300 — —	—
Collector-Emitter Saturation Voltage (1) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)		$V_{CE(sat)}$	 — —	 0.4 1.6	Vdc
Base-Emitter Saturation Voltage (1) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)		$V_{BE(sat)}$	 — —	 1.3 2.6	Vdc

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain – Bandwidth Product (1), (2) (I_C = 50 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	200	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	8.0	pF
Input Capacitance (V_{BE} = 2.0 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	—	30	pF
SWITCHING CHARACTERISTICS				
Turn-On Time (V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc) (Figures 1 and 5)	t_{on}	—	50	ns
Delay Time (V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc) (Figures 1 and 5)	t_d	—	10	ns
Rise Rime (V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc) (Figures 1 and 5)	t_r	—	40	ns
Turn-Off Time (V_{CC} = 6.0 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc) (Figure 2)	t_{off}	—	110	ns
Storage Time (V_{CC} = 6.0 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc) (Figure 2)	t_s	—	80	ns
Fall Time (V_{CC} = 6.0 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc) (Figure 2)	t_f	—	30	ns

FIGURE 1 – DELAY AND RISE TIME TEST CIRCUIT

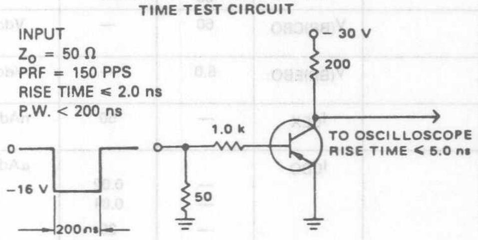
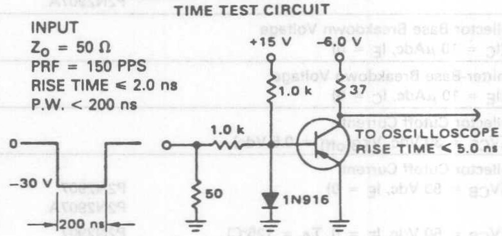
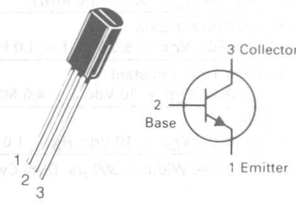


FIGURE 2 – STORAGE AND FALL TIME TEST CIRCUIT



CASE 29-03, STYLE 1
TO-92 (TO-226AE)



ONE WATT AMPLIFIER TRANSISTORS

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	80	Vdc
Collector-Base Voltage	V_{CBO}	120	Vdc
Emitter-Base Voltage	V_{EBO}	7.0	Vdc
Collector Current — Continuous	I_C	1.0	Adc
Total Device Dissipation $T_A = 25°C$ Derate above 25°C	P_D	1.0 8.0	Watts mW/°C
Total Device Dissipation $T_C = 25°C$ Derate above 25°C	P_D	2.5 20	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (1) ($I_C = 30$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	80	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)		$V_{(BR)CBO}$	120	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	7.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 90$ Vdc, $I_E = 0$) ($V_{CB} = 90$ Vdc, $I_E = 0$, $T_A = +150°C$)		I_{CBO}	 — —	 0.01 10	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$)		I_{EBO}	—	0.01	μAdc
ON CHARACTERISTICS					
DC Current Gain (1) ($I_C = 0.1$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc, $T_C = -55°C$) ($I_C = 500$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 1.0$ Adc, $V_{CE} = 10$ Vdc)	 P2N3019 P2N3019 P2N3019 P2N3019 P2N3019	h_{FE}	 50 90 100 40 50 15	 — — 300 — — —	—
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)		$V_{CE(sat)}$	 — —	 0.2 0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)		$V_{BE(sat)}$	—	1.1	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)	P2N3019	f_T	80	—	MHz

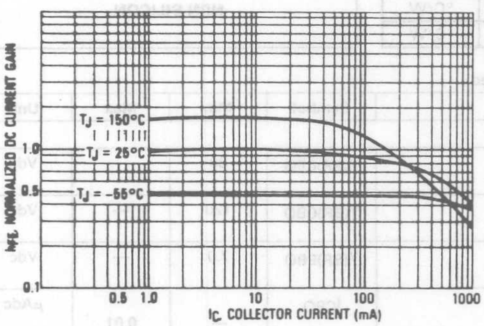
2

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

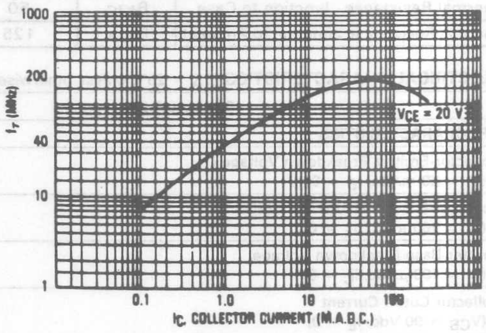
Characteristic		Symbol	Min	Max	Unit
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	12	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	60	pF
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	P2N3019	h_{fe}	80	400	—
Collector Base Time Constant (I_E = 10 mAdc, V_{CB} = 10 Vdc, f = 4.0 MHz)	P2N3019	$r_b'C_c$	—	400	ps
Noise Figure (I_C = 100 μAdc, V_{CE} = 10 Vdc, R_S = 1.0 kohms, f = 1.0 kHz)		N_F	—	4.0	dB

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 1.0%.

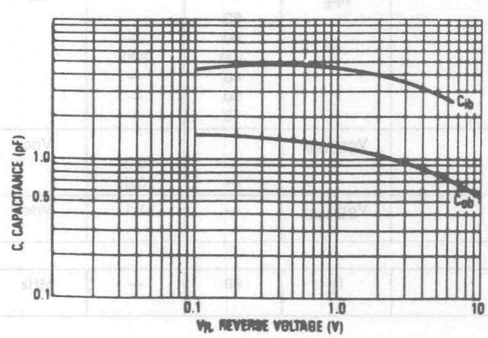
DC CURRENT GAIN
P2N3019



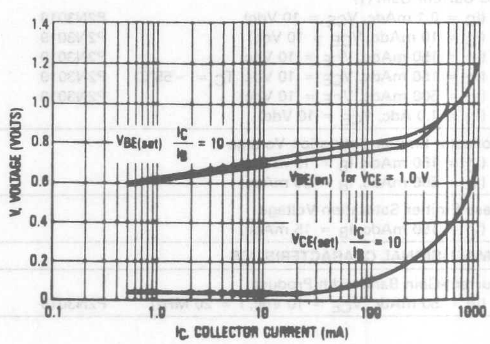
CURRENT GAIN — BANDWIDTH PRODUCT



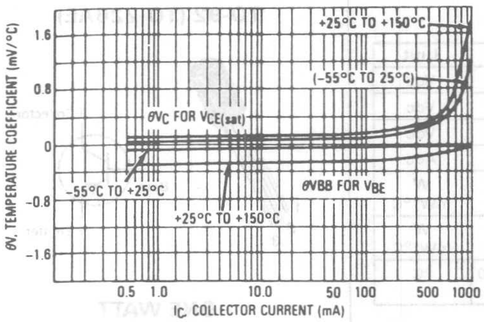
CAPACITANCE



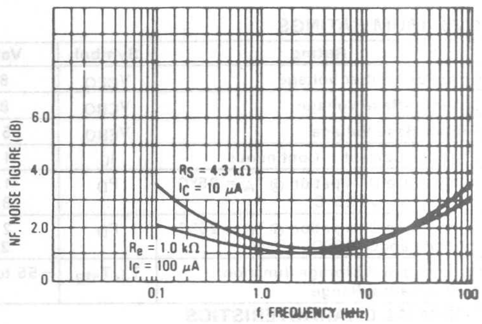
"ON" VOLTAGES



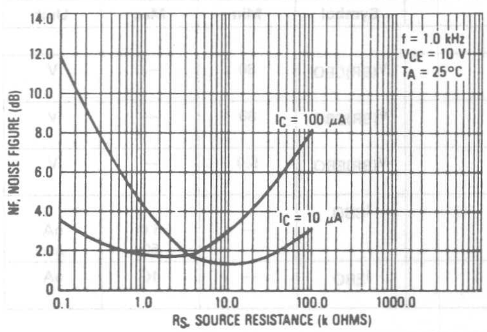
TEMPERATURE COEFFICIENTS



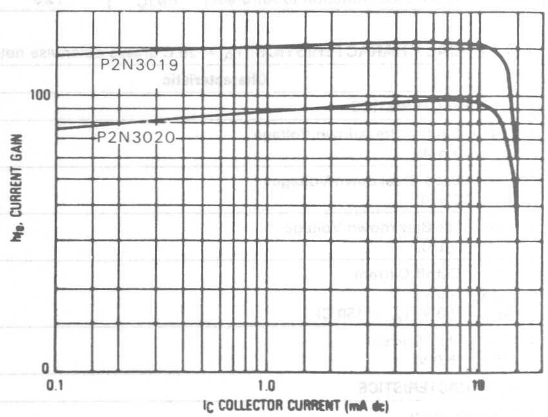
FREQUENCY EFFECTS



SOURCE RESISTANCE EFFECTS



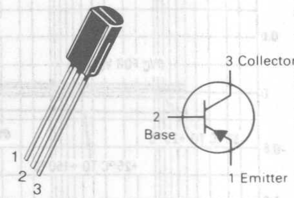
CURRENT GAIN BANDWIDTH PRODUCT versus COLLECTOR CURRENT — 1 kHz h_{fe}



2

P2N4033

CASE 29-03, STYLE 1
TO-92 (TO-226AE)



ONE WATT AMPLIFIER TRANSISTORS

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	80	Vdc
Collector-Base Voltage	V_{CBO}	80	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous	I_C	1.0	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 8.0	W mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 20	W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	125	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 10$ mA)		$V_{(BR)CEO}$	80	—	V
Collector-Base Breakdown Voltage ($I_C = 10\ \mu A$)		$V_{(BR)CBO}$	80	—	V
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu A$)		$V_{(BR)EBO}$	5.0	—	V
Collector Cutoff Current ($V_{CB} = 60$ V) ($V_{CB} = 60$ V, $T_A = 150°C$)		I_{CBO}	 — —	 5.0 50	 nA μA
Emitter Cutoff Current ($V_{EB} = 5.0$ V)		I_{EBO}	—	10	nA
ON CHARACTERISTICS					
DC Current Gain ($I_C = 100$ mA, $V_{CE} = 5.0$ V, –55°C) ($I_C = 100\ \mu A$, $V_{CE} = 5.0$ V) ($I_C = 100$ mA, $V_{CE} = 5.0$ V) ($I_C = 500$ mA, $V_{CE} = 5.0$ V) ($I_C = 1.0$ A, $V_{CE} = 5.0$ V)	 P2N4033 P2N4033 P2N4033 P2N4033 P2N4033	h_{FE}	 40 75 100 70 25	 — — 300 — —	—
Collector-Emitter Saturation Voltage ($I_C = 150$ mA, $I_B = 15$ mA) ($I_C = 500$ mA, $I_B = 50$ mA)		$V_{CE(sat)}$	 — —	 0.15 0.5	V
Base-Emitter Saturation Voltage ($I_C = 150$ mA, $I_B = 15$ mA) ($I_C = 500$ mA, $I_B = 50$ mA)		$V_{BE(sat)}$	 — —	 0.9 1.1	V

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance (V_{CE} = 10 V, f = 1.0 MHz)	C_{obo}	—	25	pF
Input Capacitance (V_{EB} = 0.5 V, f = 1.0 MHz)	C_{ibo}	—	150	pF
Current Gain — Bandwidth Product (I_C = 50 mA, V_{CC} = 10 V, f = 100 MHz)	f_T	150		MHz
SWITCHING CHARACTERISTICS				
Turn-On Time (see Figure 1) (I_C = 500 mA, I_{B1} = 50 mA)	t_{on}	—	100	ns
Turn-Off Time (see Figure 1) (I_C = 500 mA, I_{B1} = I_{B2} = 50 mA)	t_{off}	—	400	ns

(1) Pulse Width = 300 μs, Duty Cycle 1.0%.

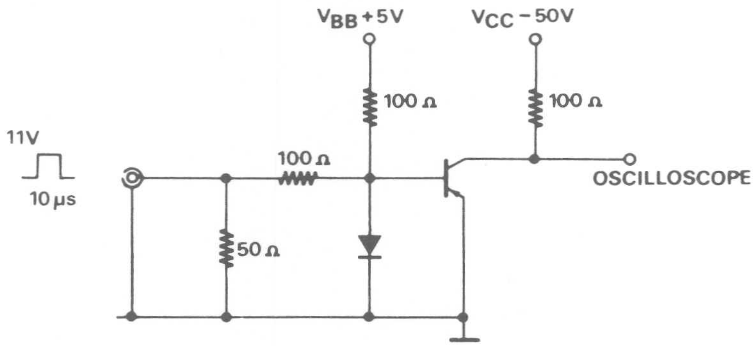
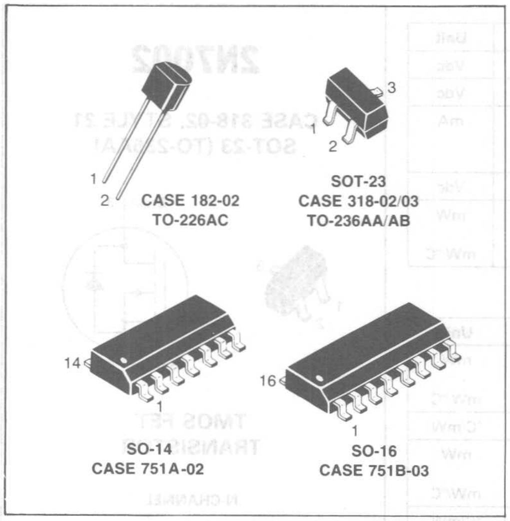


FIGURE 1: SWITCHING TIMES TEST CIRCUIT

2

Surface Mount Products

3



A wide variety of discrete components from Motorola's repertoire of reliability-proven semiconductor processes and geometries are available in the SOT-23, SO-14 and SO-16 packages. Products include Bipolar and Field-Effect Transistors, Diode Arrays, Switching Diodes, Zener and Varactor Diodes.

Contact your Motorola representative for ordering information.

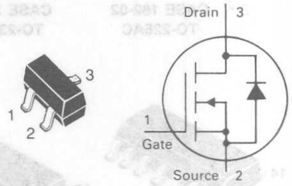
The Product Portfolio is constantly being expanded to meet the requirements for surface mount technology.

Tape and Reel is available for high volume, automated processing.

Contact the Motorola sales representative if there is a requirement for product that is not represented in this publication.

Drain Current — Continuous	T_C = 25°C(1)	I_D	±115	mA
	T_C = 100°C(1)	I_D	±75	
— Pulsed(2)		I_{DM}	±800	
Gate-Source Voltage		V_{GS}	±40	Vdc
Total Power Dissipation	T_C = 25°C	P_D	200	mW
	T_C = 100°C		80	
Derate above 25°C ambient			0.16	mW/°C

CASE 318-02, STYLE 21
SOT-23 (TO-236AA)



TMOS FET
TRANSISTOR

N-CHANNEL

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

2N7002 = 702

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 10 μA)	$V_{(BR)DSS}$	60	—	—	Vdc
Zero Gate Voltage Drain Current (V_{GS} = 0, V_{DS} = 60 V)	I_{DSS}				μAdc
T_J = 25°C		—	—	1.0	
T_J = 125°C		—	—	500	
Gate-Body Leakage Current Forward (V_{GS} = 20 Vdc)	I_{GSSF}	—	—	100	nAdc
Gate-Body Leakage Current Reverse (V_{GS} = −20 Vdc)	I_{GSSR}	—	—	−100	nAdc

(1) The Power Dissipation of the package may result in a lower continuous drain current.
(2) Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

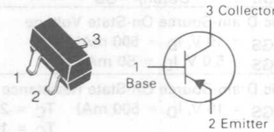
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS*						
Gate Threshold Voltage ($V_{DS} = V_{GS}$, I_D = 250 μA)		$V_{GS(th)}$	1.0	—	2.5	Vdc
On-State Drain Current ($V_{DS} \geq 2.0\ V_{DS(on)}$, V_{GS} = 10 V)		$I_{D(on)}$	500	—	—	mA
Static Drain-Source On-State Voltage		$V_{DS(on)}$				Vdc
(V_{GS} = 10 V, I_D = 500 mA)			—	—	3.75	
(V_{GS} = 5.0 V, I_D = 50 mA)			—	—	1.5	
Static Drain-Source On-State Resistance		$r_{DS(on)}$				Ohms
(V_{GS} = 10 V, I_D = 500 mA)	T_C = 25°C		—	—	7.5	
	T_C = 100°C		—	—	13.5	
(V_{GS} = 5.0 V, I_D = 50 mA)	T_C = 25°C		—	—	7.5	
	T_C = 100°C		—	—	13.5	
Forward Transconductance ($V_{DS} \geq 2.0\ V_{DS(on)}$, I_D = 200 mA)		g_{FS}	80	—	—	mmhos
DYNAMIC CHARACTERISTICS						
Input Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	—	50	pF
Output Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{oss}	—	—	25	pF
Reverse Transfer Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	—	—	5.0	pF
SWITCHING CHARACTERISTICS*						
Turn-On Delay Time	(V_{DD} = 30 V, $I_D \cong$ 200 mA,	$t_{d(on)}$	—	—	20	ns
Turn-Off Delay Time	R_G = 25 Ω, R_L = 150 Ω)	$t_{d(off)}$	—	—	20	ns
BODY-DRAIN DIODE RATINGS						
Diode Forward On-Voltage (I_S = 11.5 mA, V_{GS} = 0 V)		V_{SD}	—	—	−1.5	V
Source Current Continuous (Body Diode)		I_S	—	—	−115	mA
Source Current Pulsed		I_{SM}	—	—	−800	mA

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

BC807
BC808

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

3

MAXIMUM RATINGS

Rating	Symbol	BC807	BC808	Unit
Collector-Emitter Voltage	V_{CEO}	45	25	V
Collector-Base Voltage	V_{CBO}	50	30	V
Emitter-Base Voltage	V_{EBO}	5.0	5.0	V
Collector Current — Continuous	I_C	500	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

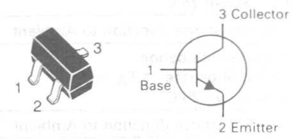
BC807-16 = 5A; BC807-25 = 5B; BC807-40 = 5C; BC808-16 = 5E;
BC808-25 = 5F; BC808-40 = 5G

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage	BC807 Series BC808 Series	$V_{(BR)CEO}$	45 25	— —	— —	V
Collector-Emitter Breakdown Voltage ($V_{EB} = 0$)	BC807 Series BC808 Series	$V_{(BR)CES}$	50 30	— —	— —	V
Emitter-Base Breakdown Voltage	BC807 Series BC808 Series	$V_{(BR)EBO}$	5.0 5.0	— —	— —	V
Collector Cutoff Current ($V_{CB} = 20$ V) ($V_{CB} = 20$ V, $T_J = 150°C$)		I_{CBO}	— —	— —	100 5.0	nA μA
ON CHARACTERISTICS						
DC Current Gain ($I_C = 100$ mA, $V_{CE} = 1.0$ V)	BC807-16 BC808-16	h_{FE}	100	—	250	
	BC807-25 BC808-25		160	—	400	
	BC807-40 BC808-40		250	—	600	
($I_C = 500$ mA, $V_{CE} = 1.0$ V)		h_{fe}	40	—	—	
Collector-Emitter Saturation Voltage ($I_C = 500$ mA, $I_B = 50$ mA)		$V_{CE(sat)}$	—	—	0.7	V
Base-Emitter On Voltage ($I_C = 500$ mA, $I_B = 1.0$ V)		$V_{BE(on)}$	—	—	1.2	V
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain Bandwidth Product ($I_C = 10$ mA, $V_{CE} = 5.0$ Vdc, f = 35 MHz)		f_T	200	—	—	MHz
Output Capacitance ($V_{CB} = 10$ V, f = 1.0 MHz)		C_{obo}	—	10	—	pF

BC817
BC818

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	BC817	BC818	Unit
Collector-Emitter Voltage	V_{CEO}	45	25	V
Collector-Base Voltage	V_{CBO}	50	30	V
Emitter-Base Voltage	V_{EBO}	5.0	5.0	V
Collector Current — Continuous	I_C	500	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BC817-16 = 6A; BC817-25 = 6B; BC817-40 = 6C; BC818-16 = 6E;
BC818-25 = 6F; BC818-40 = 6G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$				V
BC817 Series		45	—	—	
BC818 Series		25	—	—	
Collector-Emitter Breakdown Voltage (V_{EB} = 0)	$V_{(BR)CES}$				V
BC817 Series		50	—	—	
BC818 Series		30	—	—	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$				V
BC817 Series		5.0	—	—	
BC818 Series		5.0	—	—	
Collector Cutoff Current	I_{CBO}				
(V_{CB} = 20 V)		—	—	100	nA
(V_{CB} = 20 V, T_A = 150°C)		—	—	5.0	μA
ON CHARACTERISTICS					
DC Current Gain (I_C = 100 mA, V_{CE} = 1.0 V)	h_{FE}				
BC817-16, BC818-16		100	—	250	
BC817-25, BC818-25		160	—	400	
BC817-40, BC818-40		250	—	600	
(I_C = 500 mA, V_{CE} = 1.0 V)	h_{fe}	40	—	—	
Collector-Emitter Saturation Voltage (I_C = 500 mA, I_B = 50 mA)	$V_{CE(sat)}$	—	—	0.7	V
Base-Emitter On Voltage (I_C = 500 mA, V_{CE} = 1.0 V)	$V_{BE(on)}$	—	—	1.2	V
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain Bandwidth Product (I_C = 10 mA, V_{CE} = 5.0 Vdc, f = 35 MHz)	f_T	200	—	—	MHz
Output Capacitance (V_{CB} = 10 V, f = 1.0 MHz)	C_{obo}	—	10	—	pF

MAXIMUM RATINGS

Rating	Symbol	BC846	BC847	BC848	Unit
Collector-Emitter Voltage	V_{CEO}	65	45	30	V
Collector-Base Voltage	V_{CBO}	80	50	30	V
Emitter-Base Voltage	V_{EBO}	6.0	6.0	5.0	V
Collector Current — Continuous	I_C	100	100	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

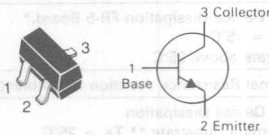
*FR-5 = 1.0 x 0.75 x 0.62 in. **Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BC846A = 1A; BC846B = 1B; BC847A = 1E; BC847B = 1F; BC847C = 1G;
BC848A = 1J; BC848B = 1K; BC848C = 1L

BC846A,B
BC847A,B,C
BC848A,B,C

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to BC546 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

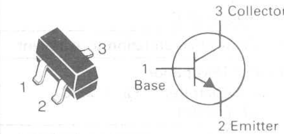
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage	BC846A,B	$V_{(BR)CEO}$	65	—	—	V
	BC847A,B,C		45	—	—	
	BC848A,B,C		30	—	—	
Collector-Emitter Breakdown Voltage ($V_{EB} = 0$)	BC846A,B	$V_{(BR)CES}$	80	—	—	V
	BC847A,B,C		50	—	—	
	BC848A,B,C		30	—	—	
Emitter-Base Breakdown Voltage	BC846A,B	$V_{(BR)EBO}$	6.0	—	—	V
	BC847A,B,C		6.0	—	—	
	BC848A,B,C		5.0			
Collector Cutoff Current		I_{CBO}				
($V_{CB} = 30$ V)			—	—	15	nA
($V_{CB} = 30$ V, $T_A = 150°C$)			—	—	5.0	μA
ON CHARACTERISTICS						
DC Current Gain ($I_C = 10$ μA, $V_{CE} = 5.0$ V)	BC846A, BC847A, BC848A	h_{FE}	—	90	—	—
	BC846B, BC847B, BC848B		—	150	—	
	BC847C, BC848C		—	270	—	
($I_C = 2.0$ mA, $V_{CE} = 5.0$ V)	BC846A, BC847A, BC848A		110	180	220	
	BC846B, BC847B, BC848B		200	290	450	
	BC847C, BC848C		420	520	800	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$				V
($I_C = 10$ mA, $I_B = 0.5$ mA)			—	—	0.25	
($I_C = 100$ mA, $I_B = 5.0$ mA)			—	—	0.6	
Base-Emitter Saturation Voltage		$V_{BE(sat)}$				V
($I_C = 10$ mA, $I_B = 0.5$ mA)			—	0.7	—	
($I_C = 100$ mA, $I_B = 5.0$ mA)			—	0.9	—	
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain Bandwidth Product ($I_C = 10$ mA, $V_{CE} = 5.0$ Vdc, f = 35 MHz)		f_T	100	—	—	MHz
Output Capacitance ($V_{CB} = 10$ V, f = 1.0 MHz)		C_{obo}	—	—	4.5	pF
Noise Figure ($I_C = 0.2$ mA, $V_{CE} = 5.0$ Vdc, $R_S = 2.0$ kΩ, f = 1.0 kHz, BW = 200 Hz)		N_F	—	—	10	dB

MAXIMUM RATINGS

Rating	Symbol	BC850	BC849	Unit
Collector-Emitter Voltage	V_{CEO}	45	30	V
Collector-Base Voltage	V_{CBO}	50	30	V
Emitter-Base Voltage	V_{EBO}	6.0	5.0	V
Collector Current — Continuous	I_C	100	100	mAdc

BC849B,C
BC850B,C

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



LOW NOISE TRANSISTOR

NPN SILICON

Refer to BC549 for graphs.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BC849B = 2B; BC849C = 2C; BC850B = 2F; BC850C = 2G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

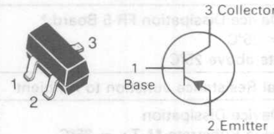
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage	BC850B,C	$V_{(BR)CEO}$	45	—	—	V
	BC849B,C		30	—	—	
Collector-Emitter Breakdown Voltage (V_{EB} = 0)	BC850B,C	$V_{(BR)CES}$	50	—	—	V
	BC849B,C		30	—	—	
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	5.0	—	—	V
Collector Cutoff Current (V_{CB} = 30 V, I_E = 0)		I_{CBO}	—	—	15	nA
(V_{CB} = 30 V, T_A = 150°C)			—	—	5.0	μA
ON CHARACTERISTICS						
DC Current Gain (I_C = 10 μA, V_{CE} = 5.0 V)	BC849B, BC850B	h_{FE}	—	150	—	—
	BC849C, BC850C		—	270	—	
(I_C = 2.0 mA, V_{CE} = 5.0 V)	BC849B, BC850B		200	290	450	
	BC849C, BC850C		420	520	800	
Collector-Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA)		$V_{CE(sat)}$	—	—	0.25	V
(I_C = 100 mA, I_B = 5.0 mA)			—	—	0.6	
Base-Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA)		$V_{BE(sat)}$	—	0.7	—	V
(I_C = 100 mA, I_B = 5.0 mA)			—	0.9	—	
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain Bandwidth Product (I_C = 10 mA, V_{CE} = 5.0 Vdc, f = 35 MHz)		f_T	100	—	—	MHz
Output Capacitance (V_{CB} = 10 V, f = 1.0 MHz)		C_{obo}	—	—	4.5	pF
Noise Figure (I_C = 0.2 mAdc, V_{CE} = 5.0 Vdc, R_S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)		N_F	—	—	4	dB

MAXIMUM RATINGS

Rating	Symbol	BC856	BC857	BC858	Unit
Collector-Emitter Voltage	V_{CEO}	65	45	30	V
Collector-Base Voltage	V_{CBO}	80	50	30	V
Emitter-Base Voltage	V_{EBO}	5.0	5.0	5.0	V
Collector Current — Continuous	I_C	100	100	100	mAdc

BC856A,B
BC857A,B,C
BC858A,B,C

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

Refer to BC556 for graphs.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in. **Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

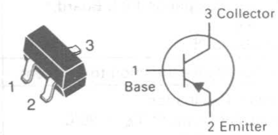
BC856A = 3A; BC856B = 3B; BC857A = 3E; BC857B = 3F; BC857C = 3G;
BC858A = 3J; BC858B = 3K; BC858C = 3L

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage	BC856 Series	$V_{(BR)CEO}$	65	—	—	V
	BC857 Series		45	—	—	
	BC858 Series		30	—	—	
Collector-Emitter Breakdown Voltage (V_{EB} = 0)	BC856 Series	$V_{(BR)CES}$	80	—	—	V
	BC857 Series		50	—	—	
	BC858 Series		30	—	—	
Emitter-Base Breakdown Voltage	BC856 Series	$V_{(BR)EBO}$	5.0	—	—	V
	BC857 Series		5.0	—	—	
	BC858 Series		5.0	—	—	
Collector Cutoff Current (V_{CB} = 30 V)		I_{CBO}	—	—	15	nA
(V_{CB} = 30 V, T_A = 150°C)			—	—	5.0	μA
ON CHARACTERISTICS						
DC Current Gain (I_C = 10 μA, V_{CE} = 5.0 V)	BC856A, BC857A, BC858A	h_{FE}	—	90	—	—
	BC856B, BC857B, BC858B		—	150	—	
	BC857C, BC858C		—	270	—	
(I_C = 2.0 mA, V_{CE} = 5.0 V)	BC856A, BC857A, BC858A		125	180	250	
	BC856B, BC857B, BC858B		220	290	475	
	BC857C, BC858C		420	520	800	
Collector-Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA)		$V_{CE(sat)}$	—	—	0.3	V
(I_C = 100 mA, I_B = 5.0 mA)			—	—	0.65	
Base-Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA)		$V_{BE(sat)}$	—	0.7	—	V
(I_C = 100 mA, I_B = 5.0 mA)			—	0.9	—	
Base-Emitter On Voltage (I_C = 2.0 mA, V_{CE} = 5.0 V)		$V_{BE(on)}$	0.6	—	0.75	V
(I_C = 10 mA, V_{CE} = 5.0 V)			—	—	0.82	
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain Bandwidth Product (I_C = 10 mA, V_{CE} = 5.0 Vdc, f = 35 MHz)		f_T	100	—	—	MHz
Output Capacitance (V_{CB} = 10 V, f = 1.0 MHz)		C_{obo}	—	—	4.5	pF
Noise Figure (I_C = 0.2 mA, V_{CE} = 5.0 Vdc, R_S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)		N_F	—	—	10	dB

BC859A,B,C
BC860A,B,C

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



LOW NOISE TRANSISTOR

PNP SILICON

3

MAXIMUM RATINGS

Rating	Symbol	BC860	BC859	Unit
Collector-Emitter Voltage	V_{CEO}	45	30	V
Collector-Base Voltage	V_{CBO}	50	30	V
Emitter-Base Voltage	V_{EBO}	6.0	5.0	V
Collector Current — Continuous	I_C	100	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BC859A = 4A; BC859B = 4B; BC859C = 4C; BC860A = 4E; BC860B = 4F; BC860C = 4G

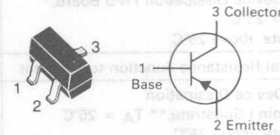
Refer to BC559 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage	BC860 Series BC859 Series	$V_{(BR)CEO}$	45 30	— —	— —	V
Collector-Emitter Breakdown Voltage (V_{EB} = 0)	BC860 Series BC859 Series	$V_{(BR)CES}$	50 30	— —	— —	V
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	5.0	—	—	V
Collector Cutoff Current (V_{CB} = 30 V, I_E = 0) (V_{CB} = 30 V, T_A = 150°C)		I_{CBO}	— —	— —	15 5.0	nA µA
ON CHARACTERISTICS						
DC Current Gain (I_C = 10 µA, V_{CE} = 5.0 V)	BC859A, BC860A BC859B, BC860B BC859C, BC860C	h_{FE}	— — —	90 150 270	— — —	—
(I_C = 2.0 mA, V_{CE} = 5.0 V)	BC859A, BC860A BC859B, BC860B BC859C, BC860C		110 200 420	180 290 520	220 450 800	
Collector-Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)		$V_{CE(sat)}$	— —	— —	0.25 0.6	V
Base-Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)		$V_{BE(sat)}$	— —	0.7 0.9	— —	V
Base-Emitter On Voltage (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 10 mA, V_{CE} = 5.0 V)		$V_{BE(on)}$	0.58 —	— —	0.7 0.77	V
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain Bandwidth Product (I_C = 10 mA, V_{CE} = 5.0 Vdc, f = 35 MHz)		f_T	100	—	—	MHz
Output Capacitance (V_{CB} = 10 V, f = 1.0 MHz)		C_{obo}	—	—	4.5	pF
Noise Figure (I_C = 0.2 mAdc, V_{CE} = 5.0 Vdc, R_S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)		N_F	—	—	4.0	dB

BCW29
BCW30

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

Refer to 2N5086 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	32	Vdc
Collector-Base Voltage	V_{CBO}	32	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BCW29 = C1; BCW30 = C2

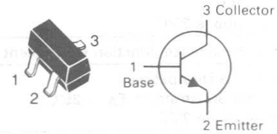
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 2.0$ mAdc, $I_E = 0$)		$V_{(BR)CEO}$	32	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 100\ \mu$Adc, $V_{EB} = 0$)		$V_{(BR)CES}$	32	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)CBO}$	32	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 32$ Vdc, $I_E = 0$) ($V_{CB} = 32$ Vdc, $I_E = 0$, $T_A = 100°C$)		I_{CBO}	— —	100 10	nAdc μAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 2.0$ mAdc, $V_{CE} = 5.0$ Vdc)	BCW29 BCW30	h_{FE}	120 215	260 500	— —
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 0.5$ mAdc)		$V_{CE(sat)}$	—	0.3	Vdc
Base-Emitter On Voltage ($I_C = 2.0$ mAdc, $V_{CE} = 5.0$ Vdc)		$V_{BE(on)}$	0.6	0.75	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance ($I_E = 0$, $V_{CE} = 10$ Vdc, f = 1.0 MHz)		C_{obo}	—	7.0	pF
Noise Figure ($I_C = 0.2$ mAdc, $V_{CE} = 5.0$ Vdc, $R_S = 2.0$ kΩ, f = 1.0 kHz, BW = 200 Hz)		NF	—	10	dB

Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	100	mAdc

BCW31
BCW33

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to MPS3904 for graphs.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

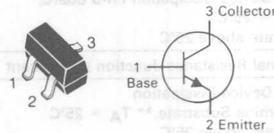
BCW31 = D1; BCW33 = D3

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 2.0 mAdc, I_B = 0)		$V_{(BR)CEO}$	20	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_B = 0)		$V_{(BR)CBO}$	30	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)	BCW31 BCW33	h_{FE}	110 420	220 800	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.5 mAdc)		$V_{CE(sat)}$	—	0.25	Vdc
Base-Emitter On Voltage (I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)		$V_{BE(on)}$	0.55	0.70	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance (I_E = 0, V_{CB} = 10 Vdc, f = 1.0 MHz)		C_{obo}	—	4.0	pF
Noise Figure (I_C = 0.2 mAdc, V_{CE} = 5.0 Vdc, R_S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)		NF	—	10	dB

BCW60A,B,C,D

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	32	V
Collector-Base Voltage	V_{CBO}	32	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current — Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BCW60A = AA; BCW60B = AB; BCW60C = AC; BCW60D = AD

Refer to MPS3904 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

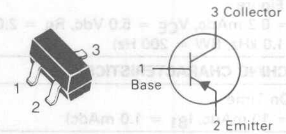
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 2.0 mAdc, I_E = 0)		$V_{(BR)CEO}$	32	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 1.0 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0		Vdc
Collector Cutoff Current (V_{CE} = 32 Vdc)		I_{CES}	—	20	nAdc
(V_{CE} = 32 Vdc, T_A = 150°C)			—	20	μAdc
Emitter Cutoff Current (V_{EB} = 4.0 Vdc, I_C = 0)		I_{EBO}	—	20	nAdc
ON CHARACTERISTICS					
DC Current Gain		h_{FE}			—
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc)	BCW60A		20	—	
	BCW60B		30	—	
	BCW60C		40	—	
	BCW60D		100	—	
(I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)	BCW60A		120	220	
	BCW60B		175	310	
	BCW60C		250	460	
	BCW60D		380	630	
(I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	BCW60A		60	—	
	BCW60B		70	—	
	BCW60C		90	—	
	BCW60D		100	—	
AC Current Gain		h_{fe}			—
(I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	BCW60A		125	250	
	BCW60B		175	350	
	BCW60C		250	500	
	BCW60D		350	700	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$			Vdc
(I_C = 50 mAdc, I_B = 1.25 mAdc)			—	0.55	
(I_C = 10 mAdc, I_B = 0.25 mAdc)			—	0.35	
Base-Emitter Saturation Voltage		$V_{BE(sat)}$			Vdc
(I_C = 50 mAdc, I_B = 1.25 mAdc)			0.7	1.05	
(I_C = 50 mAdc, I_B = 0.25 mAdc)			0.6	0.85	
Base-Emitter On Voltage (I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)		$V_{BE(on)}$	0.6	0.75	Vdc

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 MHz)	f_T	125	—	MHz
Output Capacitance (V_{CE} = 10 Vdc, I_C = 0, f = 1.0 MHz)	C_{obo}	—	4.5	pF
Noise Figure (I_C = 0.2 mAdc, V_{CE} = 5.0 Vdc, R_S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	—	6.0	dB
SWITCHING CHARACTERISTICS				
Turn-On Time (I_C = 10 mAdc, I_{B1} = 1.0 mAdc)	t_{on}	—	150	ns
Turn-Off Time (I_{B2} = 1.0 mAdc, V_{BB} = 3.6 Vdc, R_1 = R_2 = 5.0 kΩ, R_L = 990 Ω)	t_{off}	—	800	ns

BCW61A, BCW61B
BCW61C, BCW61D

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

Refer to 2N5086 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	32	V
Collector-Base Voltage	V_{CBO}	32	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current — Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BCW61A = BA; BCW61B = BB; BCW61C = BC; BCW61D = BD

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 2.0 mAdc, I_B = 0)		$V_{(BR)CEO}$	32	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 1.0 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current		I_{CES}			
(V_{CE} = 32 Vdc)			—	20	nAdc
(V_{CE} = 32 Vdc, T_A = 150°C)			—	20	μAdc
ON CHARACTERISTICS					
DC Current Gain		h_{FE}			—
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc)	BCW61A		20	—	
	BCW61B		30	—	
	BCW61C		40	—	
	BCW61D		100	—	
(I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)	BCW61A		120	220	
	BCW61B		140	310	
	BCW61C		250	460	
	BCW61D		380	630	
(I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	BCW61A		60	—	
	BCW61B		80	—	
	BCW61C		100	—	
	BCW61D		100	—	
AC Current Gain		h_{fe}			—
(I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	BCW61A		125	250	
	BCW61B		175	350	
	BCW61C		250	500	
	BCW61D		350	700	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$			Vdc
(I_C = 50 mAdc, I_B = 1.25 mAdc)			—	0.55	
(I_C = 10 mAdc, I_B = 0.25 mAdc)			—	0.25	
Base-Emitter Saturation Voltage		$V_{BE(sat)}$			Vdc
(I_C = 50 mAdc, I_B = 1.25 mAdc)			0.68	1.05	
(I_C = 50 mAdc, I_B = 0.25 mAdc)			0.6	0.85	
Base-Emitter On Voltage (I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)		$V_{BE(on)}$	0.6	0.75	Vdc

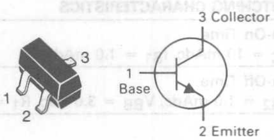
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
SMALL SIGNAL CHARACTERISTICS				
Output Capacitance (V_{CE} = 10 Vdc, I_C = 0, f = 1.0 MHz)	C_{obo}	—	6.0	pF
Noise Figure (I_C = 0.2 mAdc, V_{CE} = 5.0 Vdc, R_S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	—	6.0	dB
SWITCHING CHARACTERISTICS				
Turn-On Time (I_C = 10 mAdc, I_{B1} = 1.0 mAdc)	t_{on}	—	150	ns
Turn-Off Time (I_{B2} = 1.0 mAdc, V_{BB} = 3.6 Vdc, R_1 = R_2 = 5.0 kΩ, R_L = 990 Ω)	t_{off}	—	800	ns

3

BCW65A

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	32	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	800	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BCW65A = EA

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	32	—	—	Vdc
Collector-Emitter Breakdown Voltage (I_C = 10 μAdc, V_{EB} = 0)	$V_{(BR)CES}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CE} = 32 Vdc, I_E = 0) (V_{CE} = 32 Vdc, I_E = 0, T_A = 150°C)	I_{CES}	 — —	 — —	 20 20	 nAdc μAdc
Emitter Cutoff Current (V_{EB} = 4.0 Vdc, I_C = 0)	I_{EBO}	—	—	20	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 100 μAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc) (I_C = 100 mAdc, V_{CE} = 1.0 Vdc) (I_C = 500 mAdc, V_{CE} = 2.0 Vdc)	h_{FE}	 35 75 100 35	 — — — —	 — 220 250 —	—
Collector-Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc)	$V_{CE(sat)}$	 — —	 0.7 0.3	 — —	Vdc
Base-Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc)	$V_{BE(sat)}$	—	—	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	100	—	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	—	12	pF
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	—	—	80	pF
Noise Figure (I_C = 0.2 mAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	—	—	10	dB
SWITCHING CHARACTERISTICS					
Turn-On Time (I_{B1} = I_{B2} = 15 mAdc)	t_{on}	—	—	100	ns
Turn-Off Time (I_C = 150 mAdc, R_L = 150 Ω)	t_{off}	—	—	400	ns

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	45	Vdc
Collector-Base Voltage	V_{CBO}	75	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	800	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

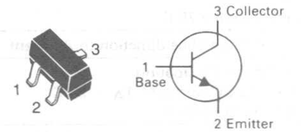
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BCW66H = EF

BCW66H

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

3

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	45	—	—	Vdc
Collector-Emitter Breakdown Voltage (I_C = 10 μAdc, V_{EB} = 0)	$V_{(BR)CES}$	75	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CE} = 45 Vdc, I_C = 0) (V_{CE} = 45 Vdc, I_C = 0, T_A = 150°C)	I_{CES}	 — —	 — —	 20 20	 nAdc μAdc
Emitter Cutoff Current (V_{EB} = 4.0 Vdc, I_C = 0)	I_{EBO}	—	—	20	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 100 μAdc, V_{CE} = 10 V) (I_C = 10 mAdc, V_{CE} = 10 V) (I_C = 100 mAdc, V_{CE} = 10 V) (I_C = 500 mAdc, V_{CE} = 2.0 Vdc)	h_{FE}	 35 75 100 35	 — — — —	 — — 250 —	—
Collector-Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc)	$V_{CE(sat)}$	 — —	 0.7 0.3	 — —	Vdc
Base-Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc)	$V_{BE(sat)}$	—	—	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	100	—	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	—	12	pF
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	—	—	80	pF
Noise Figure (I_C = 0.2 mAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	—	—	10	dB
SWITCHING CHARACTERISTICS					
Turn-On Time (I_{B1} = I_{B2} = 15 mAdc)	t_{on}	—	—	100	ns
Turn-Off Time (I_C = 150 mAdc, R_L = 150 Ω)	t_{off}	—		400	ns

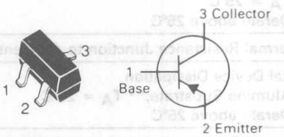
3

MAXIMUM RATINGS

Rating	Symbol	BCW67	BCW68	Unit
Collector-Emitter Voltage	V_{CEO}	32	45	Vdc
Collector-Base Voltage	V_{CBO}	45	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	5.0	Vdc
Collector Current — Continuous	I_C	800	800	mAdc

BCW67,A,B,C
BCW68,F,G

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BCW67 = DD; BCW68 = DP; BCW67A = DA; BCW67B = DB; BCW67C = DC; BCW68F = DF; BCW68G = DH

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	BCW67 Series	$V_{(BR)CEO}$	32	—	—	Vdc
	BCW68 Series		45			
Collector-Emitter Breakdown Voltage (I_C = 10 μAdc, V_{EB} = 0)	BCW67 Series	$V_{(BR)CES}$	45	—	—	Vdc
	BCW68 Series		60	—	—	
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CE} = 32 Vdc, I_E = 0)	BCW67 Series	I_{CES}	—	—	20	nAdc
(V_{CE} = 45 Vdc, I_E = 0)	BCW68 Series		—	—	20	
(V_{CE} = 32 Vdc, I_B = 0, T_A = 150°C)	BCW67 Series		—	—	10	μAdc
(V_{CE} = 45 Vdc, I_B = 0, T_A = 150°C)	BCW68 Series		—	—	10	
Emitter Cutoff Current (V_{EB} = 4.0 Vdc, I_C = 0)		I_{EBO}	—	—	20	nAdc
ON CHARACTERISTICS						
DC Current Gain (I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	BCW67,A,68,F	h_{FE}	75	—	—	—
	BCW67B,68G		120	—	—	
	BCW67C		180			
(I_C = 100 mAdc, V_{CE} = 1.0 Vdc)	BCW67,A,68,F		100		250	
	BCW67B,68G		160		400	
	BCW67C		250	—	630	
(I_C = 300 mAdc, V_{CE} = 1.0 Vdc)	BCW67,A,68,F		35	—	—	
	BCW67B,68G		60	—		
	BCW67C		100			
Collector-Emitter Saturation Voltage (I_C = 300 mAdc, I_B = 30 mAdc)		$V_{CE(sat)}$	—	—	1.5	Vdc
Base-Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc)		$V_{BE(sat)}$	—	—	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product (I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	100	—	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	—	18	pF
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	—	105	pF
Noise Figure (I_C = 0.2 mAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 kΩ, f = 1.0 kHz, BW = 200 Hz)		NF	—	—	10	dB

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	45	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

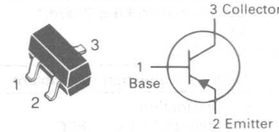
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BCW69 = H1; BCW70 = H2

BCW69
BCW70

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

3

Refer to 2N5086 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 2.0 mAdc, I_B = 0)		$V_{(BR)CEO}$	45	—	Vdc
Collector-Emitter Breakdown Voltage (I_C = 100 μAdc, V_{EB} = 0)		$V_{(BR)CES}$	50	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0) (V_{CB} = 20 Vdc, I_E = 0, T_A = 100°C)		I_{CBO}	 — —	 100 10	 nAdc μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)	BCW69 BCW70	h_{FE}	120 215	260 500	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.5 mAdc)		$V_{CE(sat)}$	—	0.3	Vdc
Base-Emitter On Voltage (I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)		$V_{BE(on)}$	0.6	0.75	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance (I_E = 0, V_{CB} = 10 Vdc, f = 1.0 MHz)		C_{obo}	—	7.0	pF
Noise Figure (I_C = 0.2 mAdc, V_{CE} = 5.0 Vdc, R_S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)		NF	—	10	dB

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	45	Vdc
Collector-Base Voltage	V_{CBO}	50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

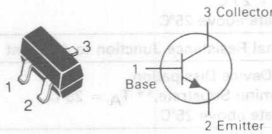
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BCW71 = K1; BCW72 = AH

BCW71
BCW72

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to MPS3904 for graphs.

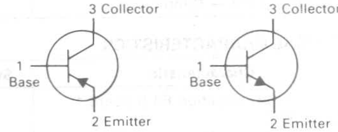
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 2.0$ mAdc, $V_{EB} = 0$)	$V_{(BR)CEO}$	45	—	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 2.0$ mAdc, $V_{EB} = 0$)	$V_{(BR)CES}$	45	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	50	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$) ($V_{CB} = 20$ Vdc, $I_E = 0$, $T_A = 100°C$)	I_{CBO}	— —	— —	100 10	nAdc μAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 2.0$ mAdc, $V_{CE} = 5.0$ Vdc) BCW71 BCW72	h_{FE}	110 200	— —	220 450	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 0.5$ mAdc) ($I_C = 50$ mAdc, $I_B = 2.5$ mAdc)	$V_{CE(sat)}$	— —	— 0.21	0.25 —	Vdc
Base-Emitter Saturation Voltage ($I_C = 50$ mAdc, $I_B = 2.5$ mAdc)	$V_{BE(sat)}$	—	0.85	—	Vdc
Base-Emitter On Voltage ($I_C = 2.0$ mAdc, $V_{CE} = 5.0$ Vdc)	$V_{BE(on)}$	0.6	—	0.75	Vdc
SMALL SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc, f = 35 MHz)	f_T	—	300	—	MHz
Output Capacitance ($I_E = 0$, $V_{CE} = 10$ Vdc, f = 1.0 MHz)	C_{obo}	—	—	4.0	pF
Input Capacitance ($I_C = 0$, $V_{EB} = 0.5$ Vdc, f = 1.0 MHz)	C_{ibo}	—	9.0	—	pF
Noise Figure ($I_C = 0.2$ mAdc, $V_{CE} = 5.0$ Vdc, $R_S = 2.0$ kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	—	—	10	dB

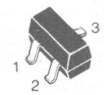
MAXIMUM RATINGS

Rating	Symbol	Value BCX17 BCX19	Value BCX18 BCX20	Unit
Collector-Emitter Voltage	V_{CEO}	45	25	Vdc
Collector-Base Voltage	V_{CBO}	50	30	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc

PNP BCX17,18 NPN BCX19,20



CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

3

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BCX17 = T1; BCX18 = T2; BCX19 = U1; BCX20 = U2

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	BCX17,19 BCX18,20	$V_{(BR)CEO}$	45 25	— —	— —	Vdc
Collector-Emitter Breakdown Voltage (I_C = 10 μAdc, I_C = 0)	BCX17,19 BCX18,20	$V_{(BR)CES}$	50 30	— —	— —	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0) (V_{CB} = 20 Vdc, I_E = 0, T_A = 150°C)		I_{CBO}	— —	— —	100 5.0	nAdc μAdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)		I_{EBO}	—	—	10	μAdc
ON CHARACTERISTICS						
DC Current Gain (I_C = 100 mAdc, V_{CE} = 1.0 Vdc) (I_C = 300 mAdc, V_{CE} = 1.0 Vdc) (I_C = 500 mAdc, V_{CE} = 1.0 Vdc)		h_{FE}	100 70 40	— — —	600 — —	—
Collector-Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc)		$V_{CE(sat)}$	—	—	0.62	Vdc
Base-Emitter On Voltage (I_C = 500 mAdc, V_{CE} = 1.0 Vdc)		$V_{BE(on)}$	—	—	1.2	Vdc

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	45	Vdc
Collector-Base Voltage	V_{CBO}	45	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

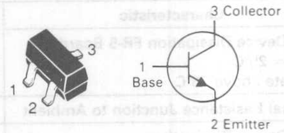
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BCX70G = AG; BCX70H = AH; BCX70J = AJ; BCX70K = AK

BCX70G,H,J,K

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to MPS3904 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 2.0$ mAdc, $I_E = 0$)		$V_{(BR)CEO}$	45	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 1.0$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 32$ Vdc)		I_{CES}	—	20	nAdc
($V_{CE} = 32$ Vdc, $T_A = 150°C$)			—	20	μAdc
Emitter Cutoff Current ($V_{EB} = 4.0$ Vdc, $I_C = 0$)		I_{EBO}	—	20	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 10$ μAdc, $V_{CE} = 5.0$ Vdc)	BCX70G	h_{FE}	—	—	
	BCX70H		20	—	
	BCX70J		40	—	
	BCX70K		100	—	
($I_C = 2.0$ mAdc, $V_{CE} = 5.0$ Vdc)	BCX70G		120	220	
	BCX70H		180	310	
	BCX70J		250	460	
	BCX70K		380	630	
($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc)	BCX70G		60	—	
	BCX70H		70	—	
	BCX70J		90	—	
	BCX70K		100	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$			Vdc
($I_C = 50$ mAdc, $I_B = 1.25$ mAdc)			—	0.55	
($I_C = 10$ mAdc, $I_B = 0.25$ mAdc)			—	0.35	
Base-Emitter Saturation Voltage		$V_{BE(sat)}$			Vdc
($I_C = 50$ mAdc, $I_B = 1.25$ mAdc)			0.7	1.05	
($I_C = 50$ mAdc, $I_B = 0.25$ mAdc)			0.6	0.85	
Base-Emitter On Voltage ($I_C = 2.0$ mAdc, $V_{CE} = 5.0$ Vdc)		$V_{BE(on)}$	0.55	0.75	Vdc

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)		f_T	125	—	MHz
Output Capacitance (V_{CE} = 10 Vdc, I_C = 0, f = 1.0 MHz)		C_{obo}	—	4.5	pF
Small-Signal Current Gain (I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)		h_{fe}			—
	BCX70G		125	250	
	BCX70H		175	350	
	BCX70J		250	500	
	BCX70K		350	700	
Noise Figure (I_C = 0.2 mAdc, V_{CE} = 5.0 Vdc, R_S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)		NF	—	6.0	dB
SWITCHING CHARACTERISTICS					
Turn-On Time (I_C = 10 mAdc, I_{B1} = 1.0 mAdc)		t_{on}	—	150	ns
Turn-Off Time (I_{B2} = 1.0 mAdc, V_{BB} = 3.6 Vdc, R1 = R2 = 5.0 kΩ, R_L = 990 Ω)		t_{off}	—	800	ns

3

3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	45	V
Collector-Base Voltage	V_{CBO}	45	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current — Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

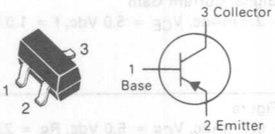
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BCX71G = BG; BCX71J = BJ; BCX71K = BK

BCX71G,J,K

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

Refer to 2N5086 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 2.0 mAdc, I_B = 0)		$V_{(BR)CEO}$	45	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 1.0 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CE} = 32 Vdc)		I_{CES}	—	20	nAdc
(V_{CE} = 32 Vdc, T_A = 150°C)			—	20	μAdc
ON CHARACTERISTICS					
DC Current Gain		h_{FE}			—
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc)	BCX71G		—	—	
	BCX71J		40	—	
	BCX71K		100	—	
(I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)	BCX71G		120	220	
	BCX71J		250	460	
	BCX71K		380	630	
(I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	BCX71G		60	—	
	BCX71J		100	—	
	BCX71K		110	—	
(I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	BCX71G		125	250	
	BCX71J		250	500	
	BCX71K		350	700	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 0.25 mAdc)			—	0.25	
(I_C = 50 mAdc, I_B = 1.25 mAdc)			—	0.55	
Base-Emitter Saturation Voltage		$V_{BE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 0.25 mAdc)			0.6	0.85	
(I_C = 50 mAdc, I_B = 1.25 mAdc)			0.68	1.05	
Base-Emitter On Voltage (I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)		$V_{BE(on)}$	0.6	0.75	Vdc
Output Capacitance (V_{CE} = 10 Vdc, I_C = 0, f = 1.0 MHz)		C_{obo}	—	6.0	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Noise Figure (I_C = 0.2 mAdc, V_{CE} = 5.0 Vdc, R_S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	—	6.0	dB
SWITCHING CHARACTERISTICS				
Turn-On Time (I_C = 10 mAdc, I_{B1} = 1.0 mAdc)	t_{on}	—	150	ns
Turn-Off Time (I_{B2} = 1.0 mAdc, V_{BB} = 3.6 Vdc, R1 = R2 = 5.0 kΩ, R_L = 990 Ω)	t_{off}	—	800	ns

3

3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Gate-Source Voltage	V_{GS}	25	Vdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

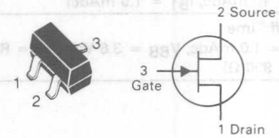
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BFR30 = M1; BFR31 = M2

BFR30
BFR31

CASE 318-02/03, STYLE 10
SOT-23 (TO-236AA/AB)



JFET AMPLIFIER

N-CHANNEL

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate Reverse Current (V_{GS} = 10 Vdc, V_{DS} = 0)		I_{GSS}	—	0.2	nAdc
Gate Source Cutoff Voltage (I_D = 0.5 nAdc, V_{DS} = 10 Vdc)	BFR30 BFR31	$V_{GS(off)}$	— —	5.0 2.5	Vdc
Gate Source Voltage (I_D = 1.0 mAdc, V_{DS} = 10 Vdc)	BFR30 BFR31	V_{GS}	0.7 —	3.0 1.3	Vdc
(I_D = 50 μAdc, V_{DS} = 10 Vdc)	BFR30 BFR31		— —	4.0 2.0	
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain (V_{DS} = 10 Vdc, V_{GS} = 0)	BFR30 BFR31	I_{DSS}	4.0 1.0	10 5.0	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance (I_D = 1.0 mAdc, V_{DS} = 10 Vdc, f = 1.0 kHz)	BFR30 BFR31	$\|Y_{fs}\|$	1.0 1.5	4.0 4.5	mAdc
(I_D = 200 μAdc, V_{DS} = 10 Vdc, f = 1.0 kHz)	BFR30 BFR31		0.5 0.75	— —	
Output Admittance (I_D = 1.0 mAdc, V_{DS} = 10 Vdc, f = 1.0 kHz) (I_D = 200 μAdc, V_{DS} = 10 Vdc)	BFR31 BFR31	$\|Y_{os}\|$	40 20	25 15	μAdc
Input Capacitance (I_D = 1.0 mAdc, V_{DS} = 10 Vdc, f = 1.0 MHz) (I_D = 200 μAdc, V_{DS} = 10 Vdc, f = 1.0 MHz)		C_{iss}	— —	5.0 4.0	pF
Reverse Transfer Capacitance (I_D = 1.0 mAdc, V_{DS} = 10 Vdc, f = 1.0 MHz) (I_D = 200 μAdc, V_{DS} = 10 Vdc, f = 1.0 MHz)		C_{rss}	— —	1.5 1.5	pF

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Base Voltage	V_{CBO}	20	Vdc
Emitter-Base Voltage	V_{EBO}	2.0	Vdc
Collector Current — Continuous	I_C	25	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

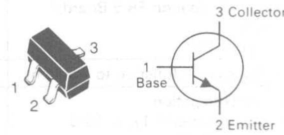
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BFR92 = P1

BFR92

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



RF TRANSISTOR

NPN SILICON

3

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mA)	$V_{(BR)CEO}$	15	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μA)	$V_{(BR)CBO}$	20	—	Vdc
Emitter-Base Breakdown Voltage (I_C = 100 μA)	$V_{(BR)EBO}$	2.0	—	Vdc
Collector Cutoff Current (V_{CB} = 10 V)	I_{CBO}	—	50	nA
ON CHARACTERISTICS				
DC Current Gain (I_C = 14 mA, V_{CE} = 10 V)(1)	h_{FE}	25	—	—
Collector-Emitter Saturation Voltage(1) (I_C = 25 mA, I_B = 5.0 mA)	$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 25 mA, I_B = 5.0 mA)	$V_{BE(sat)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 14 mA, V_{CE} = 10 V, f = 500 MHz)	f_T	5 GHz (Typ)	—	MHz
Noise Figure (V_{CE} = 1.5 V, I_C = 3.0 mA, R_S = 50 Ω, f = 500 MHz)	NF	—	3.0 (Typ)	dB
Capacitance-Collector to Base (V_{CB} = 10 Vdc, f = 1.0 MHz)	C_{cb}	—	0.7 (Typ)	pF

(1) Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	12	Vdc
Collector-Base Voltage	V_{CBO}	15	Vdc
Emitter-Base Voltage	V_{EBO}	2.0	Vdc
Collector Current — Continuous	I_C	25	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4.	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

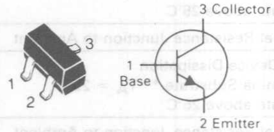
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BFR93 = R1

BFR93

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



RF TRANSISTOR

NPN SILICON

3

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 10$ mA)	$V_{(BR)CEO}$	12	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu A$)	$V_{(BR)CBO}$	15	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu A$)	$V_{(BR)EBO}$	2.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 10$ V)	I_{CEO}	—	50	nA
Collector Cutoff Current ($V_{CB} = 10$ V)	I_{CBO}	—	50	nA
Emitter Cutoff Current ($V_{EB} = 1.0$ V)	I_{EBO}		10	nA
ON CHARACTERISTICS				
DC Current Gain ($I_C = 1.0$ mA, $V_{CE} = 5.0$ V) ($I_C = 30$ mA, $V_{CE} = 5.0$ V)	h_{FE}	25 25		—
Collector-Emitter Saturation Voltage ($I_C = 35$ mA, $I_B = 7.0$ mA)	$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 35$ mA, $I_B = 7.0$ mA)	$V_{BE(sat)}$		1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 30$ mA, $V_{CE} = 5.0$ V, f = 500 MHz)	f_T	4.5	—	GHz
Noise Figure ($V_{CE} = 5.0$ V, $I_C = 2.0$ mA, $R_S = 50\ \Omega$, f = 30 MHz)	NF	—	3.0	dB

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Base Voltage	V_{CBO}	25	Vdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

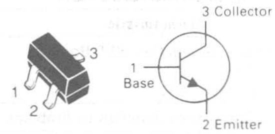
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BFS17 = E1

BFS17

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



RF TRANSISTOR

NPN SILICON

3

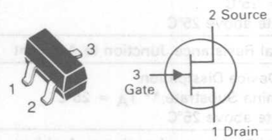
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 10 mA)	$V_{(BR)CEO}$	15	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μA)	$V_{(BR)CBO}$	25	—	Vdc
Collector Cutoff Current (V_{CE} = 10 V)	I_{CEO}	—	25	nA
Collector Cutoff Current (V_{CB} = 10 V)	I_{CBO}	—	25	nA
Emitter Cutoff Current (V_{EB} = 4.0 V)	I_{EBO}	—	100	μA
ON CHARACTERISTICS				
DC Current Gain	h_{FE}			—
(I_C = 2.0 mA, V_{CE} = 1.0 V)		20	150	
(I_C = 25 mA, V_{CE} = 1.0 V)		20	—	
Collector-Emitter Saturation Voltage (I_C = 10 mA, I_B = 1.0 mA)	$V_{CE(sat)}$	—	0.4	V
Base-Emitter Saturation Voltage (I_C = 10 mA, I_B = 1.0 mA)	$V_{BE(sat)}$	—	1.0	V
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product	f_T			GHz
(I_C = 2.0 mA, V_{CE} = 5.0 V, f = 500 MHz)		1.0	—	
(I_C = 25 mA, V_{CE} = 5.0 V, f = 500 MHz)		1.3*	—	
Output Capacitance (V_{CB} = 10 V, f = 1.0 MHz)	CCB	—	1.0*	pF
Noise Figure (I_C = 2.0 mA, V_{CE} = 5.0 V, R_S = 50 Ω, f = 30 MHz)	NF	—	5.0*	dB

*Typ

BSR56
BSR57
BSR58

CASE 318-02/03, STYLE 10
SOT-23 (TO-236AA/AB)



JFET SWITCHING TRANSISTOR

N-CHANNEL

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	$\pm V_{DS}$	40	V
Drain-Gate Voltage	V_{DG}	40	V
Gate-Source Voltage	V_{GS}	40	V
Forward Gate Current	$I_{G(f)}$	50	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

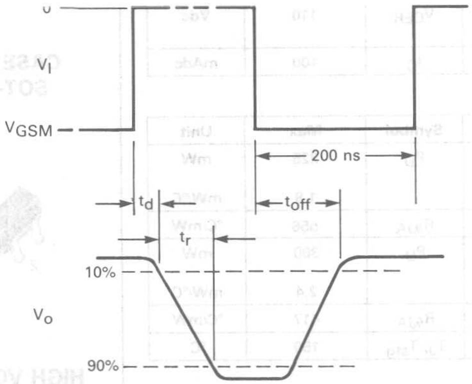
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

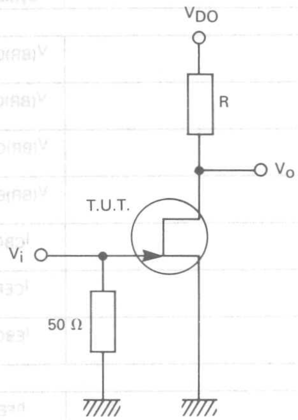
BSR56 = M4; BSR57 = M5; BSR58 = M6

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = 1.0 μAdc, V_{DS} = 0)		$V_{(BR)GSS}$	40	—	Vdc
Gate-Reverse Current (V_{DS} = 0 V, V_{GS} = 20 V)		I_{GSS}	—	1.0	nA
Gate-Source Cutoff Voltage (V_{DS} = 15 V, I_D = 0.5 nA)	BSR56 BSR57 BSR58	$V_{GS(off)}$	4.0 2.0 0.8	10 6.0 4.0	V
ON CHARACTERISTICS					
Zero-Gate Voltage Drain (V_{DS} = 15 V, V_{GS} = 0)	BSR56 BSR57 BSR58	I_{DSS}	50 20 8.0	— 100 80	mA
Drain-Source On Voltage (I_D = 20 mA, V_{GS} = 0) (I_D = 10 mA, V_{GS} = 0) (I_D = 5.0 mA, V_{GS} = 0)	BSR56 BSR57 BSR58	$V_{DS(on)}$	— — —	0.75 0.5 0.4	Vdc
Static Drain-Source On Resistance (I_D = 0 mAdc, V_{GS} = 0, f = 1.0 kHz)	BSR56 BSR57 BSR58	$r_{DS(on)}$	— — —	25 40 60	Ohms
SWITCHING CHARACTERISTICS					
Delay Time: V_{DD} = 10 V; V_{GS} = 0 (V_{GSM} = 10 V, I_D = 20 mA) (V_{GSM} = 6.0 V, I_D = 10 mA) (V_{GSM} = 4.0 V, I_D = 5.0 mA)	BSR56 BSR57 BSR58	t_d	— — —	6.0 6.0 10	ns
Rise Time: V_{DD} = 10 V; V_{GS} = 0 (V_{GSM} = 10 V, I_D = 20 mA) (V_{GSM} = 6.0 V, I_D = 10 mA) (V_{GSM} = 4.0 V, I_D = 5.0 mA)	BSR56 BSR57 BSR58	t_r	— — —	3.0 4.0 10	ns
Turn-Off Time: V_{DD} = 10 V; V_{GS} = 0 (V_{GSM} = 10 V, I_D = 20 mA (V_{GSM} = 6.0 V, I_D = 10 mA) (V_{GSM} = 4.0 V, I_D = 5.0 mA)	BSR56 BSR57 BSR58	t_{off}	— — —	25 50 100	ns



SWITCHING TIMES WAVEFORMS



BSR56; R = 464 Ω
BSR57; R = 953 Ω
BSR58; R = 1910 Ω

Pulse Generator
$t_r = t_f \leq 1.0$ ns
$\delta = 0.02$
$Z_o = 50\ \Omega$

Oscilloscope
$t_r \leq 0.75$ ns
$R_i \geq 1\ M\Omega$
$C_i \leq 2.5$ pF

3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	100	Vdc
Collector-Emitter Voltage R_{BE} = 10 kΩ	V_{CER}	110	Vdc
Collector Current — Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

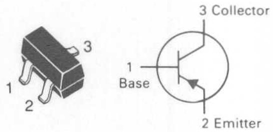
DEVICE MARKING

BSS63 = T1

3

BSS63

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



HIGH VOLTAGE TRANSISTOR

PNP SILICON

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 100 μAdc)	$V_{(BR)CEO}$	100	—	—	Vdc
Collector-Emitter Breakdown Voltage (I_C = 10 μAdc, I_E = 0, R_{BE} = 10 kΩ)	$V_{(BR)CER}$	110	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	110	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc)	$V_{(BR)EBO}$	6.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 90 Vdc, I_E = 0)	I_{CBO}	—	—	100	nAdc
Collector Cutoff Current (V_{CE} = 110 Vdc, R_{BE} = 10 kΩ)	I_{CER}	—	—	10	μAdc
Emitter Cutoff Current (V_{EB} = 6.0 Vdc, I_C = 0)	I_{EBO}	—	—	200	nAdc
ON CHARACTERISTICS					
DC Current Gain	h_{FE}				—
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)		30	—	—	
(I_C = 25 mAdc, V_{CE} = 1.0 Vdc)		30	—	—	
Collector-Emitter Saturation Voltage (I_C = 25 mAdc, I_B = 2.5 mAdc)	$V_{CE(sat)}$	—	—	250	mVdc
Base-Emitter Saturation Voltage (I_C = 25 mAdc, I_B = 2.5 mAdc)	$V_{BE(sat)}$	—	—	900	mVdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 25 mAdc, V_{CE} = 5.0 Vdc, f = 35 MHz)	f_T	50	95	—	MHz
Case Capacitance (I_E = I_C = 0, V_{CB} = 10 Vdc)	C_C	—	—	5.0	pF

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	80	Vdc
Collector-Base Voltage	V_{CBO}	120	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	100	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

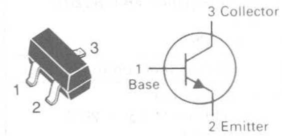
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BSS64 = AM

BSS64

CASE 318-03, STYLE 6
SOT-23 (TO-236AA/AB)



DRIVER TRANSISTOR

NPN SILICON

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 4.0 mA)	$V_{(BR)CEO}$	80	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μA)	$V_{(BR)CBO}$	120	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μA)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CE} = 90 V) (T_A = 150°C)	I_{CBO}	 — —	 0.1 500	μA
Emitter Cutoff Current (V_{BE} = 4.0 V)	I_{EBO}	—	200	nA
ON CHARACTERISTICS				
DC Current Gain (V_{CE} = 1.0 V, I_C = 10 mA)	h_{FE}	20	—	—
Collector-Emitter Saturation Voltage (I_C = 4.0 mA, I_B = 400 μA) (I_C = 50 mA, I_B = 15 mA)	$V_{CE(sat)}$	 — —	 0.15 0.2	Vdc
Forward Base-Emitter Voltage	$V_{BE(sat)}$	—	—	—
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 4.0 mA, V_{CE} = 10 V, f = 35 MHz)	f_T	60	—	MHz
Output Capacitance (V_{CE} = 10 V, f = 1.0 MHz)	C_{ob}	—	5.0	pF

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	75	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

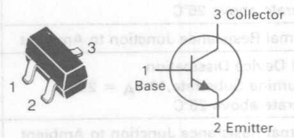
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BSS79B = CE; BSS79C = CF

BSS79B
BSS79C

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc)		$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc)		$V_{(BR)CBO}$	75	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc)		$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current (V_{CB} = 60 Vdc)		I_{CBO}	—	10	nAdc
(V_{CB} = 60 Vdc, T_A = 150°C)			—	10	μAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc)		I_{EBO}	—	10	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 150 mAdc, V_{CE} = 10 Vdc)	BSS79B	h_{FE}	40	120	—
	BSS79C		100	300	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$			Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)			—	0.3	
(I_C = 500 mAdc, I_B = 50 mAdc)			—	1.0	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (V_{CE} = 20 Vdc, I_C = 20 mAdc, f = 100 MHz)		f_T	250	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, f = 1.0 MHz)		C_{obo}	—	8.0	pF
SWITCHING CHARACTERISTICS					
Delay Time (V_{CC} = 30 Vdc, I_C = 150 mAdc) ($I_{B1} = I_{B2}$ = 15 mAdc)		t_d	—	10	ns
Rise Time (V_{CC} = 30 Vdc, I_C = 150 mAdc) ($I_{B1} = I_{B2}$ = 15 mAdc)		t_r	—	10	ns
Storage Time (V_{CC} = 30 Vdc, I_C = 150 mAdc) ($I_{B1} = I_{B2}$ = 15 mAdc)		t_s	—	225	ns
Fall Time (V_{CC} = 30 Vdc, I_C = 150 mAdc) ($I_{B1} = I_{B2}$ = 15 mAdc)		t_f	—	60	ns

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	800	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

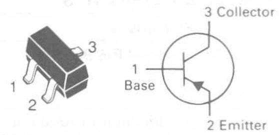
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BSS80B = CH; BSS80C = CJ

BSS80B
BSS80C

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

3

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 10 mA)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μA)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μA)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 50 Vdc) (V_{CB} = 50 Vdc, T_A = 150°C)	I_{CBO}	— —	10 10	nA μA
Emitter Cutoff Current (V_{BE} = 3.0 Vdc)	I_{EBO}	—	10	nA
ON CHARACTERISTICS				
DC Current Gain (I_C = 150 mA, V_{CE} = 10 Vdc) BSS80B BSS80C	h_{FE}	40 100	120 300	— —
Collector-Emitter Saturation Voltage (I_C = 150 mA, I_B = 15 mA) (I_C = 500 mA, I_B = 50 mA)	$V_{CE(sat)}$	— —	0.4 1.6	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 50 mA, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	200	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, f = 1.0 MHz)	C_{obo}	—	8.0	pF

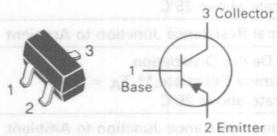
SWITCHING CHARACTERISTICS

Characteristic	Conditions	Symbol	Min	Max	Unit
Delay Time	($I_{B1} \approx I_{B2} \approx$ 15 mA, V_{CC} = 30 V, I_C = 150 mA)	t_d	—	10	ns
Rise Time		t_r	—	40	ns
Storage Time	($I_{B1} \approx I_{B2} \approx$ 15 mA, V_{CC} = 30 V, I_C = 150 mA)	t_s	—	80	ns
Fall Time		t_f	—	30	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

BSS82B
BSS82C

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	60	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

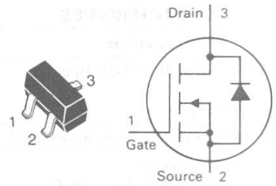
BSS82B = CH; BSS82C = CM

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 mA)		$V_{(BR)CEO}$	60	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μA)		$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μA)		$V_{(BR)EBO}$	5.0		Vdc
Collector Cutoff Current (V_{CB} = 50 V)		I_{CBO}	—	10	nA
(V_{CB} = 50 V, T_A = 150°C)			—	10	μA
Emitter Cutoff Current (V_{EB} = 3.0 V)		I_{EBO}	—	10	nA
ON CHARACTERISTICS					
DC Current Gain (I_C = 150 mA, V_{CE} = 10 V)	BSS82B	h_{FE}	40	120	—
	BSS82C		100	300	—
Collector-Emitter Saturation Voltage (I_C = 150 mA, I_B = 15 mA)		$V_{CE(sat)}$		0.4	Vdc
(I_C = 500 mA, I_B = 50 mA)			—	1.6	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 50 mA, V_{CE} = 20 V, f = 200 MHz)		f_T	100	—	MHz

Drain Current Continuous (1) Pulsed (2)	I_D I_{DM}	0.17 0.68	Adc

CASE 318-02, STYLE 21
SOT-23 (TO-236AA)



TMOS FET TRANSISTOR

N-CHANNEL

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

BSS123 = 5A

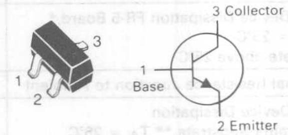
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 10 μA)		$V_{(BR)DSS}$	100	—	—	Vdc
Zero Gate Voltage Drain Current (V_{GS} = 0, V_{DS} = 100 V) T_J = 25°C T_J = 125°C		I_{DSS}	 — —	 — —	 15 60	nAdc
Gate-Body Leakage Current (V_{GS} = 20 Vdc, V_{DS} = 0)		I_{GSS}	—	—	50	nAdc
ON CHARACTERISTICS*						
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.0 mA)		$V_{GS(th)}$	0.8	—	2.8	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 100 mA)		$r_{DS(on)}$	—	5.0	6.0	Ohms
Forward Transconductance (V_{DS} = 25 V, I_D = 100 mA)		g_{fs}	80	—	—	mmhos
DYNAMIC CHARACTERISTICS						
Input Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	20	—	pF
Output Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{oss}	—	9.0	—	pF
Reverse Transfer Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	—	4.0	—	pF
SWITCHING CHARACTERISTICS*						
Turn-On Delay Time	(V_{CC} = 30 V, I_C = 0.28 A, V_{GS} = 10 V, R_{GS} = 50 Ω)	$t_{d(on)}$	—	20	—	ns
Turn-Off Delay Time		$t_{d(off)}$	—	40	—	ns
REVERSE DIODE						
Diode Forward On-Voltage (I_D = 0.34 A, V_{GS} = 0 V)		V_{SD}	—	—	1.3	V

(1) The Power Dissipation of the package may result in a lower continuous drain current.
(2) Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

BSV52

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



SWITCHING TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	100	Vdc
Gate-Source Voltage	V_{GS}	±35	Vdc
Drain Current Continuous (1) Pulsed (2)	 I_D I_{DM}	 0.17 0.68	Adc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

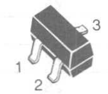
BSV52 = B2

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc)	$V_{(BR)CEO}$	12		Vdc
Collector Cutoff Current (V_{CB} = 10 Vdc, I_E = 0) (V_{CB} = 10 Vdc, I_E = 0, T_A = 125°C)	I_{CBO}	 — —	 100 5.0	 nAdc μAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc) (I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	h_{FE}	 25 40 25	 — 120 —	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 300 μAdc) (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)	$V_{CE(sat)}$	 — — —	 300 250 400	mVdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)	$V_{BE(sat)}$	 700 —	 850 1200	mVdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc)	f_T	400		MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	4.0	pF
Input Capacitance (V_{EB} = 1.0 Vdc, I_C = 0)	C_{ibo}	—	4.5	pF
SWITCHING CHARACTERISTICS				
Storage Time (I_C = I_B = I_{BM} = 10 mAdc)	t_s	—	13	ns
Turn-On Time (V_{BE} = 1.5 Vdc, I_C = 10 mAdc, I_B = 3.0 mAdc)	t_{on}	—	12	ns
Turn-Off Time (I_C = 10 mAdc, I_B = 3.0 mAdc)	t_{off}		18	ns

BZX84C4V7 thru BZX84C33

CASE 318-02/03, STYLE 8
SOT-23 (TO-236AA/AB)



ZENER DIODES

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Voltage Range	$V_{Z(nom)}$	4.7 to 33	Vdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Forward Voltage (I_F = 10 mAdc)	BZX84C Series	V_F	—	0.9	Vdc
Reverse Voltage Leakage Current		I_R			μAdc
(V_R = 2.0 Vdc)	BZX84C4V7		—	3.0	
	BZX84C5V1		—	2.0	
	BZX84C5V6		—	1.0	
(V_R = 4.0 Vdc)	BZX84C6V2		—	3.0	
	BZX84C6V8		—	2.0	
(V_R = 5.0 Vdc)	BZX84C7V5		—	1.0	
	BZX84C8V2		—	0.7	
(V_R = 6.0 Vdc)	BZX84C9V1		—	0.5	
(V_R = 7.0 Vdc)	BZX84C10		—	0.2	
(V_R = 8.0 Vdc)	BZX84C11, C12, C13		—	0.1	
(V_R = 0.70 V_Z)	BZX84C15 to BZX84C33		—	0.05	

3

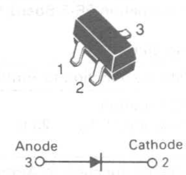
ZENER VOLTAGE

Device	Marking	I_{Z3}(mA)	V_{Z3}(V) Min	V_{Z3}(V) Max	$Z_{ZT1}(\Omega)$	$Z_{ZT2}(\Omega)$	$Z_{ZT3}(\Omega)$	$\Delta V_Z/\Delta T$(nV/k) Min	$\Delta V_Z/\Delta T$(nV/k) Max
BZX84C4V7	Z1	20	4.5	5.4	80	500	15	−3.5	0.2
BZX84C5V1	Z2	20	5.0	5.9	60	480	15	−2.7	1.2
BZX84C5V6	Z3	20	5.2	6.3	40	400	10	−2.0	2.5
BZX84C6V2	Z4	20	5.8	6.8	10	150	6	0.4	3.7
BZX84C6V8	Z5	20	6.4	7.4	15	80	6	1.2	4.5
BZX84C7V5	Z6	20	7.0	8.0	15	80	6	2.5	5.3
BZX84C8V2	Z7	20	7.7	8.8	15	80	6	3.2	6.2
BZX84C9V1	Z8	20	8.5	9.7	15	100	8	3.8	7.0
BZX84C10	Z9	20	9.4	10.7	20	150	10	4.5	8.0
BZX84C11	Y1	20	10.4	11.8	20	150	10	5.4	9.0
BZX84C12	Y2	20	11.4	12.9	25	150	10	6.0	10
BZX84C13	Y3	20	12.5	14.2	30	170	15	7.0	11
BZX84C15	Y4	20	13.9	15.7	30	200	20	9.2	13
BZX84C16	Y5	20	15.4	17.2	40	200	20	10.4	14
BZX84C18	Y6	20	16.9	19.2	45	225	20	12.4	16
BZX84C20	Y7	20	18.9	21.4	55	225	20	14.4	18
BZX84C22	Y8	20	20.9	23.4	55	250	25	16.4	20
BZX84C24	Y9	20	22.9	25.7	70	250	25	18.4	22
BZX84C27	Y10	10	25.2	29.3	80	300	45	21.4	25.3
BZX84C30	Y11	10	28.1	32.4	80	300	50	24.4	29.4
BZX84C33	Y12	10	31.1	35.4	80	325	55	27.4	33.4

Device	Marking	I_{Z1}(mA)	V_{Z1}(V) Min	V_{Z1}(V) Max	I_{Z1}(mA)	V_{Z2}(V) Min	V_{Z2}(V) Max
BZX84C4V7	Z1	5	4.4	5.0	1	3.7	4.7
BZX84C5V1	Z2	5	4.8	5.4	1	4.2	5.3
BZX84C5V6	Z3	5	5.2	6.0	1	4.8	6.0
BZX84C6V2	Z4	5	5.8	6.6	1	5.6	6.6
BZX84C6V8	Z5	5	6.4	7.2	1	6.3	7.2
BZX84C7V5	Z6	5	7.0	7.9	1	6.9	7.9
BZX84C8V2	Z7	5	7.7	8.7	1	7.6	8.7
BZX84C9V1	Z8	5	8.5	9.6	1	8.4	9.6
BZX84C10	Z9	5	9.4	10.6	1	9.3	10.6
BZX84C11	Y1	5	10.4	11.6	1	10.2	11.6
BZX84C12	Y2	5	11.4	12.7	1	11.2	12.7
BZX84C13	Y3	5	12.4	14.1	1	12.3	14
BZX84C15	Y4	5	13.8	15.6	1	13.7	15.5
BZX84C16	Y5	5	15.3	17.1	1	15.2	17
BZX84C18	Y6	5	16.8	19.1	1	16.7	19
BZX84C20	Y7	5	18.8	21.2	1	18.7	21.1
BZX84C22	Y8	5	20.8	23.3	1	20.7	23.2
BZX84C24	Y9	5	22.8	25.6	1	22.7	25.5
BZX84C27	Y10	2	25.1	28.9	0.5	25	28.9
BZX84C30	Y11	2	28	32	0.5	27.8	32
BZX84C33	Y12	2	31	35	0.5	30.8	35

MBAL99

CASE 318-02/03, STYLE 17
SOT-23 (TO-236AA/AB)



SWITCHING DIODE

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	70	Vdc
Peak Forward Current	I_F	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MBAL99 = TFX

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Voltage Leakage Current	I_R			μA
($V_R = 70$ V)		—	2.5	
($V_R = 25$ V, $T_J = 150°C$)		—	30	
($V_R = 70$ V, $T_J = 150°C$)		—	50	
Reverse Breakdown Voltage ($I_R = 100$ μA)	$V_{(BR)}$	70	—	V
Forward Voltage	V_F			mV
($I_F = 1.0$ mA)		—	715	
($I_F = 10$ mA)		—	855	
($I_F = 50$ mA)		—	1100	
($I_F = 100$ mA)		—	1300	
Recovery Current ($I_F = 10$ mA, $V_R = 5.0$ V, $R_L = 500\ \Omega$)	Q_S	—	45	pC
Diode Capacitance ($V_R = 0$, f = 1.0 MHz)	C_D	—	1.5	pF
Reverse Recovery Time ($I_F = I_R = 10$ mA, $R_L = 100\ \Omega$, measured at $I_R = 1.0$ mA)	t_{rr}	—	15	ns
Forward Recovery Voltage ($I_F = 10$ mA, $t_r = 20$ ns)	V_{FR}	—	1.75	V

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	75	Vdc
Peak Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

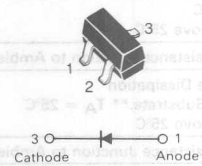
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MBAS16 = A6

MBAS16

CASE 318-02/03, STYLE 8
SOT-23 (TO-236AA/AB)



SWITCHING DIODE

3

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Voltage Leakage Current (V_R = 75 V) (V_R = 75 V, T_J = 150°C) (V_R = 25 V, T_J = 150°C)	I_R	 — — —	 1.0 50 30	μA
Reverse Breakdown Voltage (I_{BR} = 100 μA)	$V_{(BR)}$	75	—	V
Forward Voltage (I_F = 1.0 mA) (I_F = 10 mA) (I_F = 50 mA) (I_F = 100 mA)	V_F	 — — — —	 715 855 1100 1300	mV
Diode Capacitance (V_R = 0, f = 1.0 MHz)	C_D	—	2.0	pF
Forward Recovery Voltage (I_F = 10 mA, t_r = 20 ns)	V_{FR}	—	1.75	V
Reverse Recovery Time (I_F = I_R = 10 mA, R_L = 100 Ω)	t_{rr}	—	15	ns
Stored Charge (I_F = 10 mA to V_R = 5.0 V, R_L = 500 Ω)	Q_S	—	45	pC

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

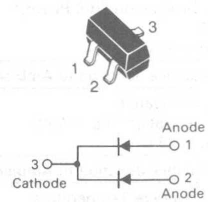
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MBAV70 = A4X

MBAV70

CASE 318-02/03, STYLE 9
SOT-23 (TO-236AA/AB)



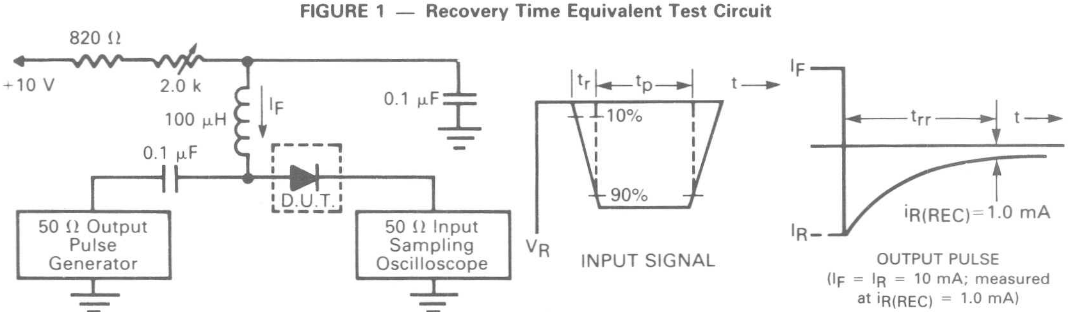
SWITCHING DIODE

3

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_{(BR)}$ = 100 μAdc)	$V_{(BR)}$	>70	—	Vdc
Reverse Voltage Leakage Current (V_R = 25 Vdc, T_J = 150°C) (V_R = 70 Vdc) (V_R = 70 Vdc, T_J = 150°C)	I_R	 — — —	 60 5.0 100	μAdc
Diode Capacitance (V_R = 0, f = 1.0 MHz)	C_D	—	1.5	pF
Forward Voltage (I_F = 1.0 mAdc) (I_F = 10 mAdc) (I_F = 50 mAdc) (I_F = 100 mAdc)	V_F	 — — — —	 715 855 1100 1300	mVdc
Reverse Recovery Time (I_F = I_R = 10 mAdc, V_R = 5.0 Vdc, $I_{R(REC)}$ = 1.0 mAdc) (Figure 1)	t_{rr}	—	15	ns

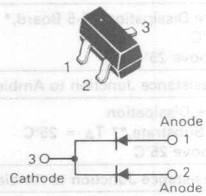
FIGURE 1 — Recovery Time Equivalent Test Circuit



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

MBAV74

CASE 318-02/03, STYLE 9
SOT-23 (TO-236AA/AB)



SWITCHING DIODE

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	50	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

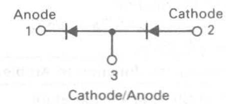
MBAV74 = JAX

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_{(BR)} = 5.0\ \mu Adc$)	$V_{(BR)}$	50	—	Vdc
Reverse Voltage Leakage Current	I_R			μAdc
($V_R = 50$ Vdc, $T_J = 125°C$)		—	100	
($V_R = 50$ Vdc)		—	0.1	
Diode Capacitance ($V_R = 0$, f = 1.0 MHz)	C_D	—	2.0	pF
Forward Voltage ($I_F = 100$ mAdc)	V_F	—	1.0	Vdc
Reverse Recovery Time ($I_F = I_R = 10$ mAdc, $i_{R(REC)} = 1.0$ mAdc, measured at $I_R = 1.0$ mA, $R_L = 100\ \Omega$)	t_{rr}	—	15	ns

MBAV99

CASE 318-02/03, STYLE 11
SOT-23 (TO-236AA/AB)



DUAL SERIES SWITCHING DIODE

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	100	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

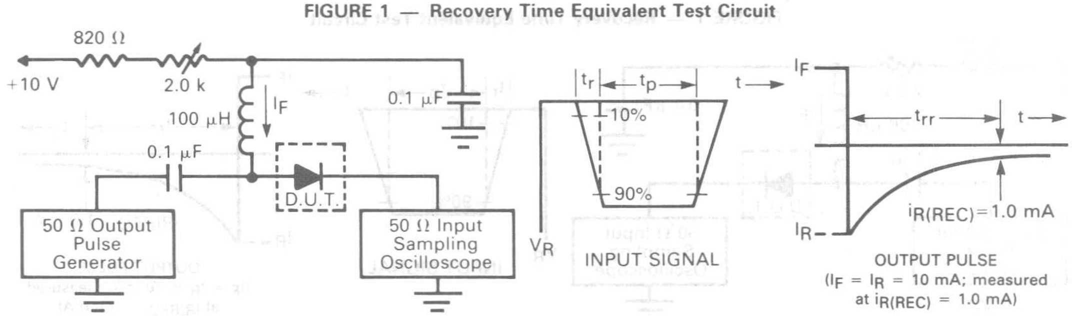
DEVICE MARKING

MBAV99 = A7X

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_{(BR)} = 100\ \mu A$)	$V_{(BR)}$	70	—	Vdc
Reverse Voltage Leakage Current	I_R			μAdc
(V_R = 25 Vdc, T_J = 150°C)		—	30	
(V_R = 70 Vdc)		—	2.5	
(V_R = 70 Vdc, T_J = 150°C)		—	50	
Diode Capacitance (V_R = 0, f = 1.0 MHz)	C_D	—	1.5	pF
Forward Voltage	V_F			mVdc
(I_F = 1.0 mAdc)		—	715	
(I_F = 10 mAdc)		—	855	
(I_F = 50 mAdc)		—	1100	
(I_F = 100 mAdc)		—	1300	
Reverse Recovery Time ($I_F = I_R$ = 10 mAdc, $i_{R(REC)}$ = 1.0 mAdc) (Figure 1)	t_{rr}	—	15	ns

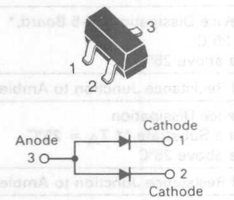
FIGURE 1 — Recovery Time Equivalent Test Circuit



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

MBAW56

CASE 318-02/03, STYLE 12
SOT-23 (TO-236AA/AB)



DUAL SWITCHING DIODE

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

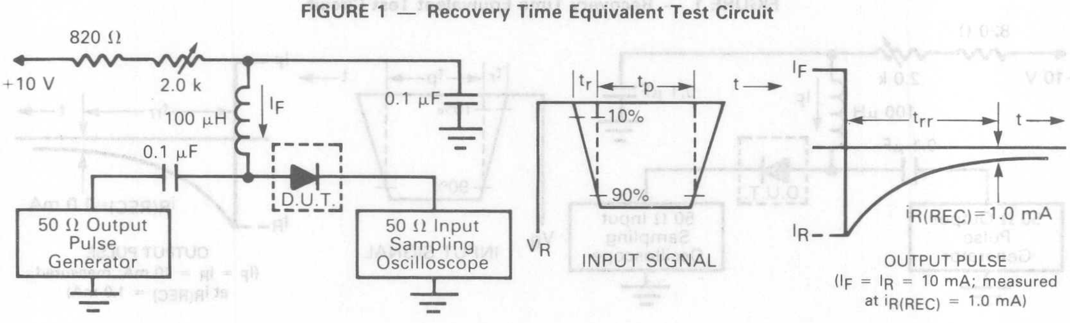
DEVICE MARKING

MBAW56 = A1X

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_{(BR)} = 100\ \mu Adc$)	$V_{(BR)}$	70	—	Vdc
Reverse Voltage Leakage Current	I_R			μAdc
($V_R = 25$ Vdc, $T_J = 150°C$)		—	30	
($V_R = 70$ Vdc)		—	2.5	
($V_R = 70$ Vdc, $T_J = 150°C$)		—	50	
Diode Capacitance ($V_R = 0$, f = 1.0 MHz)	C_D	—	2.5	pF
Forward Voltage	V_F			mVdc
($I_F = 1.0$ mAdc)		—	715	
($I_F = 10$ mAdc)		—	855	
($I_F = 50$ mAdc)		—	1100	
($I_F = 100$ mAdc)		—	1300	
Reverse Recovery Time ($I_F = I_R = 10$ mAdc, $I_{R(REC)} = 1.0$ mAdc) (Figure 1)	t_{rr}	—	15	ns

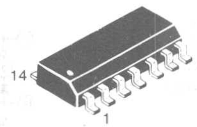
FIGURE 1 — Recovery Time Equivalent Test Circuit



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

MMAD130
MMAD1103
thru
MMAD1107
MMAD1109

CASE 751A-02
SO-14



MONOLITHIC DIODE ARRAYS

3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	50	Vdc
Steady-State Reverse Voltage	V_R	40	Vdc
Peak Forward Current 25°C	I_{FM}	500	mA
Continuous Forward Current	I_F	400	mA
Power Dissipation Derating Factor	P_D	500 4.0	mW mW/°C
Operating Temperature	T_A	−65 to +125	°C
Storage Temperature Range	T_{stg}	−65 to +150	°C

ELECTRICAL CHARACTERISTICS (@ 25°C Free-Air Temperature)

Characteristic	Symbol	Limit Min	Limit Max	Unit
Reverse Breakdown Voltage (1) (I_R = 10 μA)	$V_{(BR)}$	50	—	Vdc
Static Reverse Current (V_R = 40 V)	I_R	—	0.1	μA
Static Forward Voltage (I_F = 100 mA) (I_F = 500 mA) (2)	V_F	— —	1.1 1.5	Vdc
Peak Forward Voltage (3) (I_F = 500 mA)	V_{FM}	—	5.0	Vdc

SWITCHING CHARACTERISTICS (@ 25°C Free-Air Temperature)

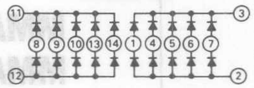
Characteristic	Symbol	Typical Value	Unit
Forward Recovery Time (I_F = 500 mA)	t_{fr}	20	ns
Reverse Recovery Time (I_F = 200 mA, I_{RM} = 200 mA, R_L = 100 Ω, i_{rr} = 20 mA)	t_{rr}	8.0	ns

1. This parameter must be measured using pulse techniques. PW = 100 μs, duty cycle ≤ 20%.
2. This parameter is measured using pulse techniques. PW = 300 μs, duty cycle ≤ 2.0%. Read time is 90 μs from the leading edge of the pulse.
3. The initial instantaneous value is measured using pulse techniques. PW = 150 ns, duty cycle ≤ 2.0%, pulse rise time ≤ 10 ns. The total capacitance shunting the diode is 19 pF maximum and the equipment bandwidth is 80 MHz.

SO-14 Pin Diagram

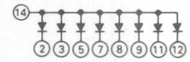
1.
Dual 10 Diode Array

MMAD130



5.
8 Diode Array (Common Anode)

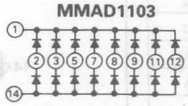
MMAD1106



NC Pin 1, 4, 6, 10, 13

2.
16 Diode Array

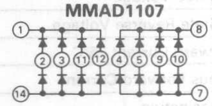
MMAD1103



NC Pin 4, 6, 10, 13

6.
Dual 8 Diode Array

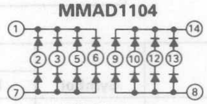
MMAD1107



NC Pin 6, 13

3.
Dual 8 Diode Array

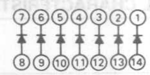
MMAD1104



NC Pin 4, 11

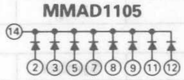
7.
7 Diode Array (Independant)

MMAD1109



4.
8 Diode Array (Common Cathode)

MMAD1105

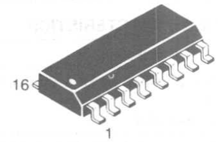


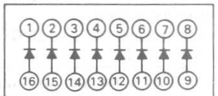
NC Pin 1, 4, 6, 10, 13

Device	Description	Diagram
MMAD130	Dual 10 Diode Array	1
MMAD1103	16 Diode Array	2
MMAD1104	Dual 8 Diode Array	3
MMAD1105	8 Diode Array Common Cathode	4
MMAD1106	8 Diode Array Common Anode	5
MMAD1107	Dual 8 Diode Array	6
MMAD1109	7 Diode Array	7

MMAD1108

CASE 751B-03
SO-16





Pin Connections Diagram

MONOLITHIC DIODE ARRAY

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	50	Vdc
Steady-State Reverse Voltage	V_R	40	Vdc
Peak Forward Current 25°C	I_{FM}	500	mA
Continuous Forward Current	I_F	400	mA
Power Dissipation Derating Factor	P_D	500 4.0	mW mW/°C
Operating Temperature	T_A	−65 to +125	°C
Storage Temperature Range	T_{stg}	−65 to +150	°C

ELECTRICAL CHARACTERISTICS (@ 25°C Free-Air Temperature)

Characteristic	Symbol	Limit Min	Limit Max	Unit
Reverse Breakdown Voltage (1) (I_R = 10 μA)	$V_{(BR)}$	50	—	Vdc
Static Reverse Current (V_R = 40 V)	I_R	—	0.1	μA
Static Forward Voltage (I_F = 100 mA) (I_F = 500 mA) (2)	V_F	 — —	 1.1 1.5	Vdc
Peak Forward Voltage (3) (I_F = 500 mA)	V_{FM}	—	5.0	Vdc

SWITCHING CHARACTERISTICS (@ 25°C Free-Air Temperature)

Characteristic	Symbol	Typical Value	Unit
Forward Recovery Time (I_F = 500 mA)	t_{fr}	20	ns
Reverse Recovery Time (I_F = 200 mA, I_{RM} = 200 mA, R_L = 100 Ω, i_{rr} = 20 mA)	t_{rr}	8.0	ns

1. This parameter must be measured using pulse techniques. PW = 100 μs, duty cycle ≤ 20%.
2. This parameter is measured using pulse techniques. PW = 300 μs, duty cycle ≤ 2.0%. Read time is 90 μs from the leading edge of the pulse.
3. The initial instantaneous value is measured using pulse techniques. PW = 150 ns, duty cycle ≤ 2.0%, pulse rise time ≤ 10 ns. The total capacitance shunting the diode is 19 pF maximum and the equipment bandwidth is 80 MHz.

Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	50	mAdc

THERMAL CHARACTERISTICS

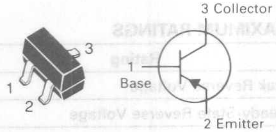
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBA811C5 = C5; MMBA811C6 = C6; MMBA811C7 = C7; MMBA811C8 = C8

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



AMPLIFIER TRANSISTOR

PNP SILICON

Refer to 2N5086 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc)	$V_{(BR)CEO}$	45	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc)	$V_{(BR)CBO}$	50	—	Vdc
Emitter-Base Breakdown Voltage ($I_C = 10$ μAdc)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 40$ Vdc)	I_{CBO}	—	50	nAdc
Emitter Cutoff Current ($V_{EB} = 5.0$ Vdc)	I_{EBO}	—	50	nAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 3.0$ Vdc) ($I_C = 0.5$ mAdc, $V_{CE} = 3.0$ Vdc) (For Reference Only) ($I_C = 0.5$ mAdc, $V_{CE} = 3.0$ Vdc) MMBA811C5 MMBA811C6 MMBA811C7 MMBA811C8	h_{FE}	 150 135 135 200 300 450	 900 270 400 600 900	—
Collector-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)	$V_{CE(sat)}$	—	0.3	Vdc
Base-Emitter On Voltage ($I_C = 0.5$ mAdc, $V_{CE} = 3.0$ Vdc)	$V_{BE(on)}$	0.5	0.65	Vdc
SMALL SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 1.0$ mAdc, $V_{CE} = 6.0$ Vdc, f = 100 MHz)	f_T	75	—	MHz

Collector-Base Voltage	V_{CBO}	[illegible]	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

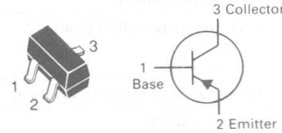
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBA812M3 = M3; MMBA812M4 = M4; MMBA812M5 = M5;
MMBA812M6 = M6; MMBA812M7 = M7

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

Refer to 2N5086 for graphs.

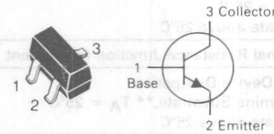
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector Cutoff Current ($V_{CB} = 40$ Vdc, $I_E = 0$)		I_{CBO}	—	0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 5.0$ Vdc, $I_C = 0$)		I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain ($V_{CE} = 6.0$ Vdc, $I_C = 1.0$ mAdc)		h_{FE}			—
	MMBA812M3		60	120	
	MMBA812M4		90	180	
	MMBA812M5		135	270	
	MMBA812M6		200	400	
	MMBA812M7		300	600	
Collector-Emitter Saturation Voltage ($I_C = 30$ mAdc, $I_B = 3.0$ mAdc)		$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter On Voltage ($V_{CE} = 6.0$ Vdc, $I_C = 1.0$ mAdc)		$V_{BE(on)}$	—	0.8	Vdc

3

MMBC1009F1
MMBC1009F3

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



AM/FM RF AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	50	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

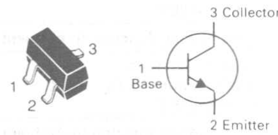
MMBC1009F1 = F1; MMBC1009F3 = F3

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_E = 0$)		I_{CBO}	—	—	0.1	μAdc
ON CHARACTERISTICS						
DC Current Gain ($I_C = 0.5$ mAdc, $V_{CE} = 3.0$ Vdc)	MMBC1009F1	h_{FE}	30	—	60	
	MMBC1009F3		60	—	120	
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)		$V_{CE(sat)}$	—	—	0.3	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain Bandwidth Product ($I_C = 1.0$ mAdc, $V_{CE} = 6.0$ Vdc, f = 100 MHz)		f_T	150	—	—	MHz
Output Capacitance ($V_{CB} = 6.0$ V, $I_E = 0$, f = 1.0 MHz)		C_{obo}	—	2.0	—	pF
Noise Figure ($I_C = 0.5$ mAdc, $V_{CE} = 6.0$ Vdc, f = 1.0 MHz, $R_G = 500$ Ω)		NF	—	2.5	—	dB

MMBC1321Q3 thru MMBC1321Q5

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



VHF/RF AMPLIFIER TRANSISTOR

NPN SILICON

3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	10	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

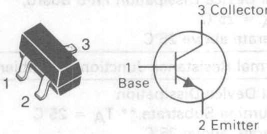
MMBC1321Q3 = Q3; MMBC1321Q4 = Q4; MMBC1321Q5 = Q5

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector Cutoff Current (V_{CB} = 25 Vdc, I_E = 0)		I_{CBO}	—	—	0.1	μAdc
Emitter Cutoff Current (V_{EB} = 4.0 Vdc, I_C = 0)		I_{EBO}	—	—	0.1	μAdc
ON CHARACTERISTICS						
DC Current Gain (I_C = 2.0 mAdc, V_{CE} = 6.0 Vdc)	MMBC1321Q3 MMBC1321Q4 MMBC1321Q5	h_{FE}	60 90 135	— — —	120 180 270	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{CE(sat)}$	—	—	0.6	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product (I_C = 2.0 mAdc, V_{CE} = 6.0 Vdc, f = 100 MHz)		f_T	600	—	—	MHz
Output Capacitance (V_{CB} = 6.0 Vdc, I_E = 0, f = 100 MHz)		C_{obo}	—	1.3	1.8	pF
Noise Figure (V_{CE} = 6.0 Vdc, I_E = 2.0 mAdc, f = 900 MHz, R_G = 50 Ω)		NF	—	5.0	—	dB

MMBC1622D6
MMBC1622D7

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MPS3904 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	35	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBC1622D6 = D6; MMBC1622D7 = D7

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector Cutoff Current (V_{CB} = 25 Vdc, I_E = 0)		I_{CBO}	—	50	nAdc
Emitter Cutoff Current (V_{EB} = 5.0 Vdc, I_C = 0)		I_{EBO}	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain (V_{CE} = 3.0 Vdc, I_C = 0.1 mAdc)	All	h_{FE}	150	—	
(V_{CE} = 3.0 Vdc, I_C = 0.5 mAdc)	MMBC1622D6		200	400	
	MMBC1622D7		300	600	
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 10 mAdc)		$V_{CE(sat)}$	—	0.3	Vdc
Base-Emitter On Voltage (V_{CE} = 3.0 Vdc, I_C = 0.5 mAdc)		$V_{BE(on)}$	0.55	0.65	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (V_{CE} = 6.0 Vdc, I_E = 1.0 mAdc, f = 100 Mhz)		f_T	100	—	MHz

Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

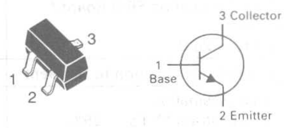
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBC1623L3 = L3; MMBC1623L4 = L4; MMBC1623L5 = L5;
MMBC1623L6 = L6; MMBC1623L7 = L7

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MPS3904 for graphs.

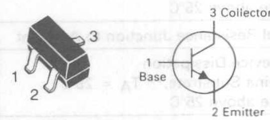
3

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector Cutoff Current (V_{CB} = 40 Vdc, I_E = 0)		I_{CBO}	—	100	nAdc
Emitter Cutoff Current (V_{EB} = 5.0 Vdc, I_C = 0)		I_{EBO}	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 6.0 Vdc)	MMBC1623L3 MMBC1623L4 MMBC1623L5 MMBC1623L6 MMBC1623L7	h_{FE}	60 90 135 200 300	120 180 270 400 600	—
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 10 mAdc)		$V_{CE(sat)}$	—	0.3	Vdc
Base-Emitter Saturation Voltage (I_C = 100 mA, I_B = 10 mAdc)		$V_{BE(sat)}$	—	1.0	Vdc
Base-Emitter On Voltage (I_C = 1.0 mAdc, V_{CE} = 6.0 Vdc)		$V_{BE(on)}$	.60	0.7	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (V_{CE} = 6.0 Vdc, I_E = 10 mAdc, f = 100 MHz)		f_T	200	—	MHz

MMBC1653N2,3,4

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



HIGH VOLTAGE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	130	Vdc
Collector-Base Voltage	V_{CBO}	150	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	50	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBC1653N2 = N2; MMBC1653N3 = N3; MMBC1653N4 = N4

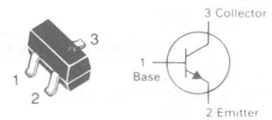
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector Cutoff Current (V_{CB} = 100 Vdc, I_E = 0)		I_{CBO}	—	—	0.1	μAdc
Emitter Cutoff Current (V_{EB} = 5.0 Vdc, I_C = 0)		I_{EBO}	—	—	0.1	μAdc
ON CHARACTERISTICS						
DC Current Gain (V_{CE} = 3.0 Vdc, I_C = 15 mAdc)		h_{FE}				—
	MMBC1653N2		50	—	130	
	MMBC1653N3		100	—	220	
	MMBC1653N4		150	—	330	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{CE(sat)}$	—	—	0.5	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{BE(sat)}$	—	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product (V_{CE} = 10 Vdc, I_E = 10 mAdc, f = 100 MHz)		f_T	—	150	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	4.5	—	pF

3

MMBC1654N5,6,7

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



HIGH VOLTAGE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	160	Vdc
Collector-Base Voltage	V_{CBO}	180	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	50	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBC1654N5 = N5; MMBC1654N6 = N6; MMBC1654N7 = N7

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector Cutoff Current ($V_{CB} = 100$ V, $I_E = 0$)		I_{CBO}	—	—	0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 5.0$ Vdc, $I_C = 0$)		I_{EBO}	—	—	0.1	μAdc
ON CHARACTERISTICS						
DC Current Gain ($V_{CE} = 3.0$ V, $I_C = 15$ mAdc)	MMBC1654N5 MMBC1654N6 MMBC1654N7	h_{FE}	50 100 150	— — —	130 220 330	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)		$V_{CE(sat)}$	—	—	0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)		$V_{BE(sat)}$	—	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product ($V_{CE} = 10$ Vdc, $I_E = 10$ mAdc, f = 100 MHz)		f_T	—	150	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{obo}	—	4.5	—	pF

THERMAL CHARACTERISTICS

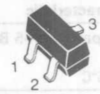
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBD101 = 4M

CASE 318-02/03, STYLE 8
SOT-23 (TO-236AA/AB)



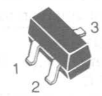
HOT-CARRIER
UHF MIXER DIODE

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Reverse Breakdown Voltage (I_R = 10 μAdc)	$V_{(BR)}$	4.0	—	—	Vdc
Reverse Voltage Leakage Current (V_R = 3.0 Vdc)	I_R	—	—	0.25	μAdc
Series Inductance (f = 250 MHz)	L_S	—	6.0	—	nH
Case Capacitance (f = 1.0 MHz)	C_C	—	0.18	—	pF
Diode Capacitance (V_R = 0, f = 1.0 MHz)	C_T	—	—	1.0	pF
Forward Voltage (I_F = 10 mAdc)	V_F	—	—	0.60	Vdc
Noise Figure (f = 1.0 GHz)	NF	—	6.0	—	dB

MMBD201
MMBD301
MMBD501
MMBD701

CASE 318-02/03, STYLE 8
SOT-23 (TO-236AA/AB)



HOT-CARRIER DIODE

3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	50	Vdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBD201 = 4S; MMBD301 = 4T; MMBD501 = 5F; MMBD701 = 5H

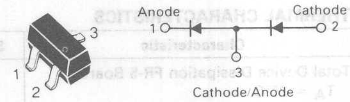
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Reverse Breakdown Voltage (I_R = 10 μAdc)	MMBD201 MMBD301 MMBD501 MMBD701	$V_{(BR)}$	20 30 50 70	— — — —	— — — —	Vdc
Reverse Voltage Leakage Current (V_R = 25 Vdc)		I_R	—	—	200	μAdc
Diode Capacitance (V_R = 20 Vdc, f = 1.0 MHz)		C_T	—	—	1.0	pF
Forward Voltage (I_F = 10 mAdc)		V_F	—	—	1.2	Vdc

3

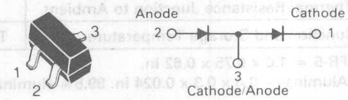
MMBD352

CASE 318-02/03 STYLE 11
SOT-23 (TO-236AA/AB)



MMBD353

CASE 318-02/03 STYLE 19
SOT-23 (TO-236AA/AB)



DUAL HOT CARRIER MIXER DIODE

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	4.0	V_{CC}

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBD352 = 5G; MMBD353 = 4F

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Forward Voltage ($I_F = 10$ mA)	V_F	—	0.60	V
Reverse Voltage Leakage Current	I_R			μA
($V_R = 3.0$ V)		—	0.25	
($V_R = 4.0$ V)		—	10	
Capacitance ($V_R = 0$ V, f = 1.0 MHz)	C	—	1.0	pF

MMBD501, MMBD701

For Specifications, See MMBD201 Data.

MMBD914X

CASE 318-02/03, STYLE 8
SOT-23 (TO-236AA/AB)

HIGH-SPEED SWITCHING DIODE

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

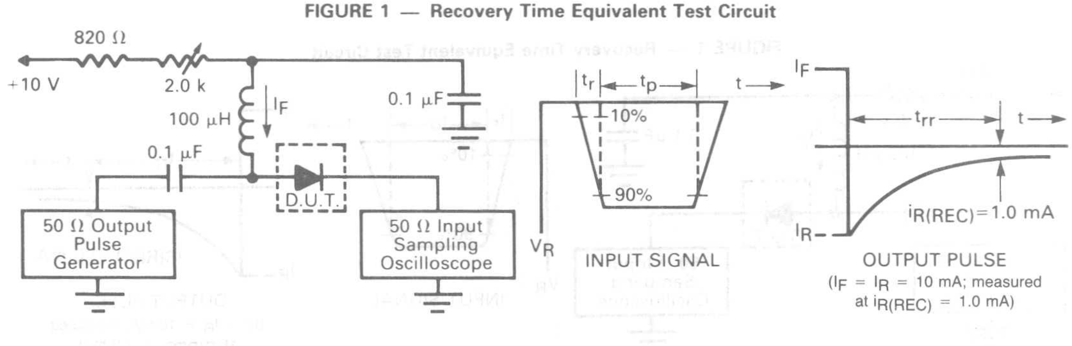
DEVICE MARKING

MMBD914X = 5D

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage (I_R = 100 μAdc)	$V_{(BR)}$	100	—	Vdc
Reverse Voltage Leakage Current	I_R			
(V_R = 20 Vdc)		—	25	nAdc
(V_R = 75 Vdc)		—	5.0	μAdc
Diode Capacitance (V_R = 0, f = 1.0 MHz)	C_T	—	4.0	pF
Forward Voltage (I_F = 1.0 mAdc)	V_F	—	1.0	Vdc
Reverse Recovery Time (I_F = I_R = 10 mAdc) (Figure 1)	t_{rr}	—	15	ns

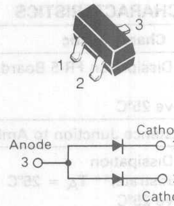
FIGURE 1 — Recovery Time Equivalent Test Circuit



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

Forward Current	I_F	100	mAdc

CASE 318-02/03, STYLE 12
SOT-23 (TO-236AA/AB)



DUAL SWITCHING DIODE

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

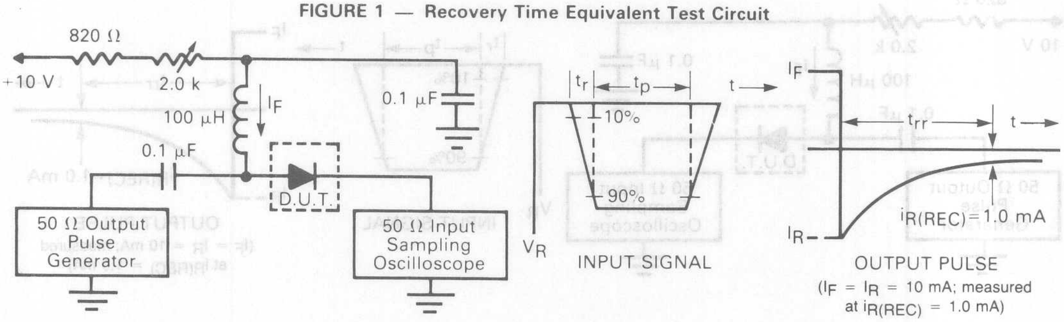
DEVICE MARKING

MMBD2835X = A3X; MMBD2836X = A2X

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Reverse Breakdown Voltage (I_R = 100 μAdc)	MMBD2835X MMBD2836X	$V_{(BR)}$	35 75	— —	Vdc
Reverse Voltage Leakage Current (V_R = 30 Vdc) (V_R = 50 Vdc)	MMBD2835X MMBD2836X	I_R	— —	100 100	nAdc
Diode Capacitance (V_R = 0, f = 1.0 MHz)		C_T	—	4.0	pF
Forward Voltage (I_F = 10 mAdc) (I_F = 50 mAdc) (I_F = 100 mAdc)		V_F	— — —	1.0 1.0 1.2	Vdc
Reverse Recovery Time (I_F = I_R = 10 mAdc, $i_{R(REC)}$ = 1.0 mAdc) (Figure 1)		t_{rr}	—	15	ns

FIGURE 1 — Recovery Time Equivalent Test Circuit



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

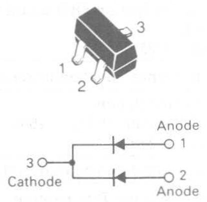
	I_{FM}	300	mAdc
Average Rectified Current	I_O	150 100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

CASE 318-02/03, STYLE 9
SOT-23 (TO-236AA/AB)



DUAL SWITCHING DIODE

3

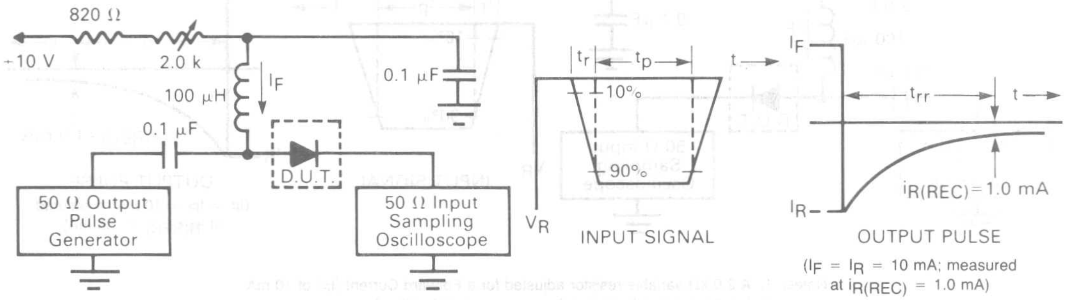
DEVICE MARKING

MMBD2837X = A5X; MMBD2838X = A6X

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Reverse Breakdown Voltage ($I_{(BR)}$ = 100 μAdc)	 MMBD2837X MMBD2838X	$V_{(BR)}$	 35 75	 — —	Vdc
Reverse Voltage Leakage Current (V_R = 30 Vdc) (V_R = 50 Vdc)	 MMBD2837X MMBD2838X	I_R	 — —	 0.1 0.1	μAdc
Diode Capacitance (V_R = 0, f = 1.0 MHz)		C_T	—	4.0	pF
Forward Voltage (I_F = 10 mAdc) (I_F = 50 mAdc) (I_F = 100 mAdc)		V_F	 — — —	 1.0 1.0 1.2	Vdc
Reverse Recovery Time (I_F = I_R = 10 mAdc, $i_{R(REC)}$ = 1.0 mAdc) (Figure 1)		t_{rr}	—	15	ns

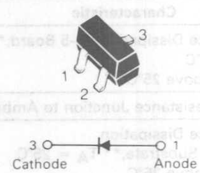
FIGURE 1 — Recovery Time Equivalent Test Circuit



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

MMBD6050X

CASE 318-02/03, STYLE 8
SOT-23 (TO-236AA/AB)



SWITCHING DIODE

3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

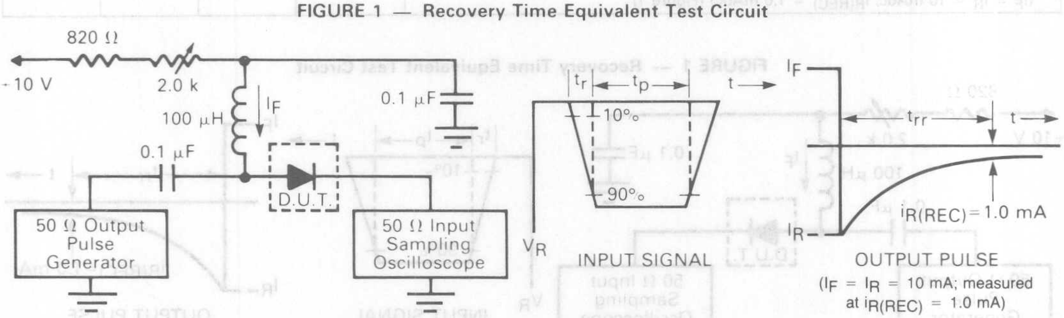
DEVICE MARKING

MMBD6050X = 5A

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_{(BR)} = 100\ \mu Adc$)	$V_{(BR)}$	70	—	Vdc
Reverse Voltage Leakage Current ($V_R = 50$ Vdc)	I_R	—	0.1	μAdc
Forward Voltage	V_F			Vdc
($I_F = 1.0$ mAdc)		0.55	0.7	
($I_F = 100$ mAdc)		0.85	1.1	
Reverse Recovery Time ($I_F = I_R = 10$ mAdc, $i_{R(REC)} = 1.0$ mAdc) (Figure 1)	t_{rr}	—	15	ns
Capacitance ($V_R = 0$)	C	—	2.5	pF

FIGURE 1 — Recovery Time Equivalent Test Circuit



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

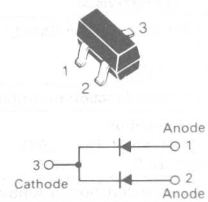
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBD6100 = 5B

MMBD6100

CASE 318-02/03, STYLE 9
SOT-23 (TO-236AA/AB)



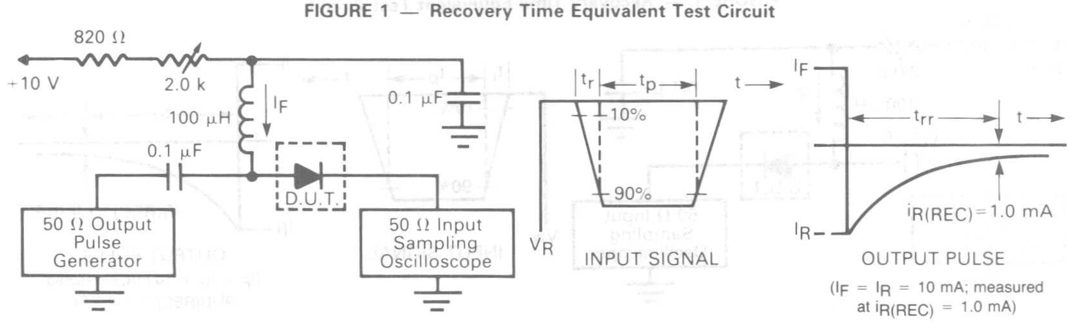
DUAL SWITCHING DIODE

3

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_{(BR)}$ = 100 μAdc)	$V_{(BR)}$	70	—	Vdc
Reverse Voltage Leakage Current (V_R = 50 Vdc)	I_R	—	0.1	μAdc
Forward Voltage	V_F			Vdc
(I_F = 1.0 mAdc)		0.55	0.7	
(I_F = 100 mAdc)		0.85	1.1	
Reverse Recovery Time ($I_F = I_R$ = 10 mAdc, $i_{R(REC)}$ = 1.0 mAdc) (Figure 1)	t_{rr}	—	15	ns
Capacitance (V_R = 0)	C	—	2.5	pF

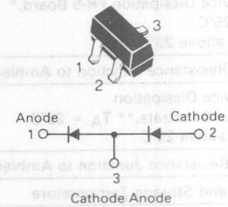
FIGURE 1 — Recovery Time Equivalent Test Circuit



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

MMBD7000

CASE 318-02/03, STYLE 11
SOT-23 (TO-236AA/AB)



DUAL SWITCHING DIODE

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	100	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

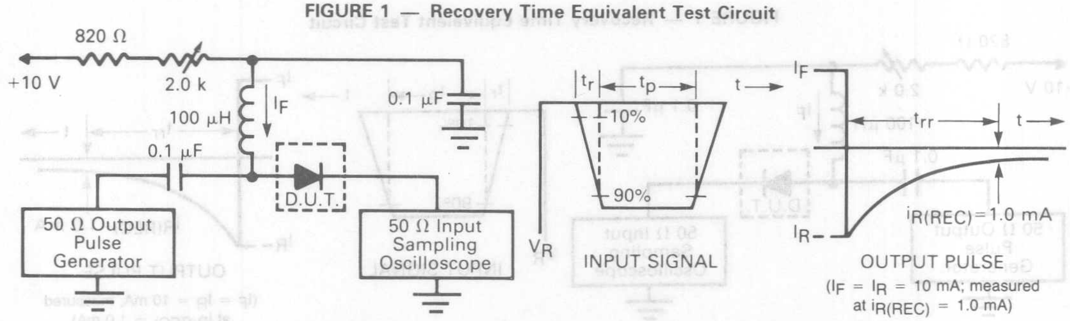
DEVICE MARKING

MMBD7000 = 5C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_{(BR)}$ = 100 μAdc)	$V_{(BR)}$	100	—	Vdc
Reverse Voltage Leakage Current				μAdc
(V_R = 50 Vdc)	I_R	—	0.30	
(V_R = 100 Vdc)	I_{R2}	—	0.5	
(V_R = 50 Vdc, 125°C)	I_{R3}	—	100	
Forward Voltage	V_F			Vdc
(I_F = 1.0 mAdc)		0.55	0.7	
(I_F = 10 mAdc)		0.67	0.82	
(I_F = 100 mAdc)		0.75	1.1	
Reverse Recovery Time (I_F = I_R = 10 mAdc) (Figure 1)	t_{rr}	—	15	ns
Capacitance (V_R = 0)	C	—	1.5	pF

FIGURE 1 — Recovery Time Equivalent Test Circuit



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p » t_{rr}$

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	Vdc
Drain-Gate Voltage	V_{DGS}	60	Vdc
Gate-Source Voltage	V_{GS}	±20	Vdc
Drain Current — Continuous Pulsed	I_D I_{DM}	0.5 0.8	Adc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

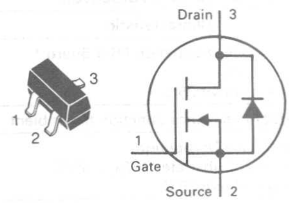
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBF170 = 6Z

MMBF170

CASE 318-02, STYLE 21
SOT-23 (TO-236AA)



TMOS FET TRANSISTOR

N-CHANNEL

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 100 μA)	$V_{(BR)DSS}$	60	—	Vdc
Gate-Body Leakage Current, Forward (V_{GSF} = 15 Vdc, V_{DS} = 0)	I_{GSS}	—	10	nAdc
ON CHARACTERISTICS*				
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.0 mA)	$V_{GS(th)}$	0.8	3.0	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 200 mA)	$r_{DS(on)}$	—	5.0	Ohm
On-State Drain Current (V_{DS} = 25 V, V_{GS} = 0)	$I_{D(off)}$	—	0.5	μA
DYNAMIC CHARACTERISTICS				
Input Capacitance (V_{DS} = 10 V, V_{GS} = 0 V, f = 1.0 MHz)	C_{iss}	—	60	pF
SWITCHING CHARACTERISTICS*				
Turn-On Delay Time (V_{DD} = 25 V, I_D = 500 mA, R_{gen} = 50 Ohms) Figure 1	$t_{d(on)}$	—	10	ns
Turn-Off Delay Time (V_{DD} = 25 V, I_D = 500 mA, R_{gen} = 50 Ohms) Figure 1	$t_{d(off)}$	—	10	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

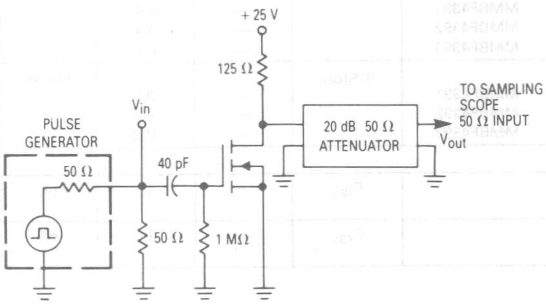
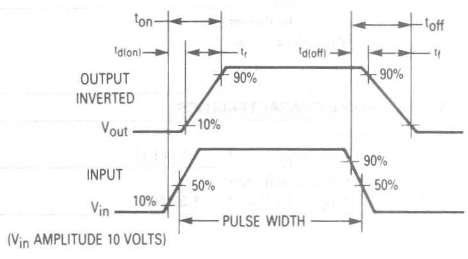


Figure 1. Switching Test Circuit

SWITCHING WAVEFORM



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage	V_{GS}	30	Vdc
Forward Gate Current	$I_{G(f)}$	50	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

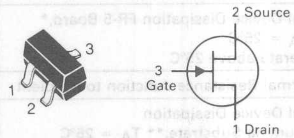
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBF4391 = 6J; MMBF4392 = 6K; MMBF4393 = 6G

MMBF4391 thru MMBF4393

CASE 318-02/03, STYLE 10
SOT-23 (TO-236AA/AB)



JFET SWITCHING TRANSISTOR
N-CHANNEL

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = 1.0 μAdc, V_{DS} = 0)		$V_{(BR)GSS}$	30	—	Vdc
Gate Reverse Current (V_{GS} = 15 Vdc, V_{DS} = 0, T_A = 25°C) (V_{GS} = 15 Vdc, V_{DS} = 0, T_A = 100°C)		I_{GSS}	— —	1.0 0.20	nAdc μAdc
Gate Source Cutoff Voltage (V_{DS} = 15 Vdc, I_D = 10 nAdc)	MMBF4391 MMBF4392 MMBF4393	$V_{GS(off)}$	4.0 2.0 0.5	10 5.0 3.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain (V_{DS} = 15 V, V_{GS} = 0)	MMBF4391 MMBF4392 MMBF4393	I_{DSS}	50 25 5.0	150 75 30	mAdc
Drain Current (V_{DS} = 15 Vdc, V_{GS} = 12 Vdc) (V_{DS} = 15, V_{GS} = 12 Vdc, T_A = 100°C)		I_D	— —	1.0 1.0	nAdc μAdc
Drain-Source On-Voltage (I_D = 12 mAdc, V_{GS} = 0) (I_D = 6.0 mAdc, V_{GS} = 0) (I_D = 3.0 mAdc, V_{GS} = 0)	MMBF4391 MMBF4392 MMBF4393	$V_{DS(on)}$	— — —	0.4 0.4 0.4	Vdc
Static Drain-Source On Resistance (I_D = 1.0 mAdc, V_{GS} = 0)	MMBF4391 MMBF4392 MMBF4393	$r_{DS(on)}$	— — —	30 60 100	Ohms
SMALL-SIGNAL CHARACTERISTICS					
Input Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	14	pF
Reverse Transfer Capacitance (V_{DS} = 0, V_{GS} = 12 Vdc, f = 1.0 MHz)		C_{rss}	—	3.5	pF

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage	V_{GS}	30	Vdc
Gate Current	I_G	10	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

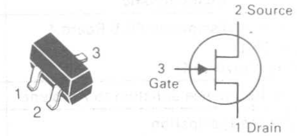
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBF4416 = 6A

MMBF4416

CASE 318-02/03, STYLE 10
SOT-23 (TO-236AA/AB)



JFET
VHF/UHF AMPLIFIER TRANSISTOR
N-CHANNEL

3

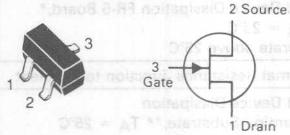
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage (I_G = 1.0 μAdc, V_{DS} = 0)	$V_{(BR)GSS}$	30	—	Vdc
Gate Reverse Current (V_{GS} = 20 Vdc, V_{DS} = 0)	I_{GSS}	—	1.0	nAdc
(V_{GS} = 20 Vdc, V_{DS} = 0, T_A = 150°C)		—	200	nAdc
Gate Source Cutoff Voltage (I_D = 1.0 nAdc, V_{DS} = 15 Vdc)	$V_{GS(off)}$	—	6.0	Vdc
Gate Source Voltage (I_D = 0.5 mAdc, V_{DS} = 15 Vdc)	V_{GS}	1.0	5.5	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain (V_{GS} = 15 Vdc, V_{GS} = 0)	I_{DSS}	5.0	15	mAdc
Gate-Source Forward Voltage (I_G = 1.0 mAdc, V_{DS} = 0)	$V_{GS(f)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)	$\|Y_{fs}\|$	4500	7500	μmhos
Output Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)	$\|Y_{os}\|$	—	50	μmhos
Input Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	4.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{rss}	—	0.8	pF
Output Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{oss}	—	2.0	pF
FUNCTIONAL CHARACTERISTICS				
Noise Figure	NF			dB
(V_{DS} = 15 Vdc, I_D = 5.0 mAdc, R_g ≈ 1000 Ω, f = 100 MHz)		—	2.0	
(V_{DS} = 15 Vdc, I_D = 5.0 mAdc, R_g ≈ 1000 Ω, f = 400 MHz)		—	4.0	
Common Source Power Gain	G_{ps}			dB
(V_{DS} = 15 Vdc, I_D = 5.0 mAdc, f = 100 MHz)		18	—	
(V_{DS} = 15 Vdc, I_D = 5.0 mAdc, f = 400 MHz)		10	—	

3

Drain-Gate Voltage	V_{DG}	30	Vdc
Reverse Gate-Source Voltage	$V_{GS(r)}$	30	Vdc
Forward Gate Current	$I_{G(f)}$	50	mAdc

CASE 318-02/03, STYLE 10
SOT-23 (TO-236AA/AB)



JFET
SWITCHING TRANSISTOR
N-CHANNEL

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

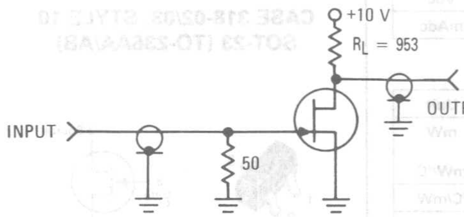
DEVICE MARKING

MMBF4860 = 6F

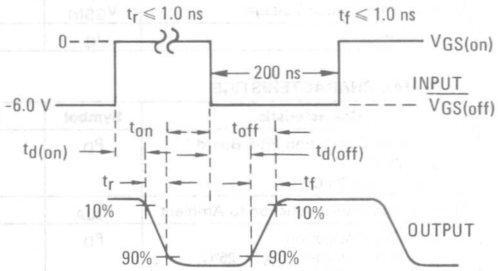
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage (I_G = 1.0 μAdc, V_{DS} = 0)	$V_{(BR)GSS}$	30	—	Vdc
Gate Reverse Current (V_{GS} = 15 Vdc, V_{DS} = 0) (V_{GS} = 15 Vdc, V_{DS} = 0, T_A = 150°C)	I_{GSS}	— —	0.5 2.0	nAdc μAdc
Gate Source Cutoff Voltage (V_{DS} = 15 Vdc, I_D = 0.5 nAdc)	$V_{GS(off)}$	2.0	6.0	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain(1) (V_{DS} = 15 Vdc, V_{GS} = 0)	I_{DSS}	20	100	mAdc
Drain Cutoff Current (V_{DS} = 15 Vdc, V_{GS} = 10 Vdc) (V_{DS} = 15 Vdc, V_{GS} = 10 Vdc, T_A = 150°C)	$I_{D(off)}$	— —	0.25 0.5	nAdc μAdc
Drain-Source On-Voltage (I_D = 10 mAdc, V_{GS} = 0)	$V_{DS(on)}$	—	0.5	Vdc
Static Drain-Source On Resistance (V_{GS} = 0, I_D = 0, f = 1.0 kHz)	$r_{DS(on)}$	—	40	Ohms
Input Capacitance (V_{DS} = 0, V_{GS} = 10 Vdc, f = 1.0 MHz)	C_{iss}	—	18	pF
Reverse Transfer Capacitance (V_{DS} = 0, V_{GS} = 10 Vdc, f = 1.0 MHz)	C_{rss}	—	8.0	pF
SWITCHING CHARACTERISTICS				
Delay Time (V_{DD} = 10 Vdc, $I_{D(on)}$ = 20 mAdc) ($V_{G(on)}$ = 0, $V_{GS(off)}$ = 10 Vdc)	t_d	—	6.0	ns
Rise Time (V_{DD} = 10 Vdc, $I_{D(on)}$ = 10 mAdc) ($V_{GS(on)}$ = 0, $V_{GS(off)}$ = 6.0 Vdc) (Figure 1)	t_r	—	4.0	ns
Turn-Off Time (V_{DD} = 10 Vdc, $I_{D(on)}$ = 5.0 mAdc) ($V_{GS(on)}$ = 0, $V_{GS(off)}$ = 4.0 Vdc) (Figure 1)	t_{off}		50	ns

(1) Pulse Test: Pulse Width = 100 ms, Duty Cycle ≤ 10%.



TEST CIRCUIT



VOLTAGE WAVEFORMS

NOTES: 1. The input waveforms are supplied by a generator with the following characteristics:
Z_{out} = 50 ohms, Duty Cycle ≈ 2.0%
2. Waveforms are monitored on an oscilloscope with the following characteristics:
$t_r \leq 0.75$ ns, $R_{in} \geq 1.0$ megohm, $C_{in} \leq 2.5$ pF.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG}	25	Vdc
Reverse Gate-Source Voltage	$V_{GS(r)}$	25	Vdc
Gate Current	I_G	10	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

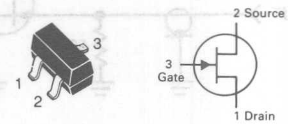
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBF5457 = 6D

MMBF5457

CASE 318-02/03, STYLE 10
SOT-23 (TO-236AA/AB)



JFET
GENERAL PURPOSE TRANSISTOR

N-CHANNEL

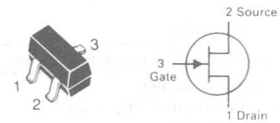
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = 10\ \mu Adc$, $V_{DS} = 0$)	$V_{(BR)GSS}$	25	—	—	Vdc
Gate Reverse Current	I_{GSS}				nAdc
($V_{GS} = 15$ Vdc, $V_{DS} = 0$)		—	—	1.0	
($V_{GS} = 15$ Vdc, $V_{DS} = 0$, $T_A = 100°C$)		—	—	200	
Gate Source Cutoff Voltage ($V_{DS} = 15$ Vdc, $I_D = 10$ nAdc)	$V_{GS(off)}$	0.5	—	6.0	Vdc
Gate Source Voltage ($V_{DS} = 15$ Vdc, $I_D = 100\ \mu Adc$)	V_{GS}	—	2.5	—	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain(1) ($V_{DS} = 15$ Vdc, $V_{GS} = 0$)	I_{DSS}	1.0	—	5.0	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance(1) ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 1.0 kHz)	$\|Y_{fs}\|$	1000	—	5000	μmhos
Reverse Transfer Admittance ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 1.0 kHz)	$\|y_{rs}\|$	—	10	50	μmhos
Input Capacitance ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 1.0 MHz)	C_{iss}	—	4.5	7.0	pF
Reverse Transfer Capacitance ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 1.0 MHz)	C_{rss}	—	1.5	3.0	pF

(1) Pulse test: Pulse Width ≤ 630 ms; Duty Cycle ≤ 10%.

MMBF5459

CASE 318-02/03, STYLE 10
SOT-23 (TO-236AA/AB)



JFET TRANSISTOR

N-CHANNEL

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V_{DG}	25	Vdc
Reverse Gate-Source Voltage	$V_{GS(r)}$	−25	Vdc
Gate Current	I_G	10	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBF5459 = 6L

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage (I_G = −10 μA, V_{DS} = 0)	$V_{(BR)GSS}$	25	—	Vdc
Gate 1 Leakage Current (V_{GS} = −15 V, V_{DS} = 0)	I_{G1SS}	—	1.0	nA
Gate 2 Leakage Current (V_{GS} = −15 V, V_{DS} = 0, T_A = 100°C)	I_{G2SS}	—	200	nA
Gate Source Cutoff Voltage (V_{DS} = 15 V, I_D = 10 nA)	$V_{GS(off)}$	2.0	8.0	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain (V_{DS} = 15 V, V_{GS} = 0)	I_{DSS}	4.0	16	mA
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance (V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz)	$\|Y_{fs}\|$	2000	6000	μmhos
Output Admittance (V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz)	$\|Y_{os}\|$	—	50	μmhos
Input Capacitance (V_{DS} = 15 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	7.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 V, V_{GS} = 0, f = 1.0 MHz)	C_{rss}	—	3.0	pF

Reverse Gate-Source Voltage	V_{GSR}	40	Vdc
Forward Gate Current	I_{GF}	10	mAdc

THERMAL CHARACTERISTICS

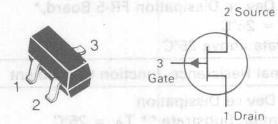
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBF5460 = 6E

CASE 318-02/03, STYLE 10
SOT-23 (TO-236AA/AB)



JFET
GENERAL PURPOSE TRANSISTOR
P-CHANNEL

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = 10 μAdc, V_{DS} = 0)	$V_{(BR)GSS}$	40	—	—	Vdc
Gate Reverse Current (V_{GS} = 20 Vdc, V_{DS} = 0) (V_{GS} = 20 Vdc, V_{DS} = 0, T_A = 100°C)	I_{GSS}	— —	— —	5.0 1.0	nAdc μAdc
Gate Source Cutoff Voltage (V_{DS} = 15 Vdc, I_D = 1.0 μAdc)	$V_{GS(off)}$	0.75	—	6.0	Vdc
Gate Source Voltage (V_{DS} = 15 Vdc, I_D = 0.1 mAdc)	V_{GS}	0.5	—	4.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain (V_{DS} = 15 Vdc, V_{GS} = 0)	I_{DSS}	1.0	—	5.0	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)	$\|Y_{fs}\|$	1000	—	4000	μmhos
Output Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)	$\|y_{os}\|$	—	—	75	μmhos
Input Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	5.0	7.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{rss}	—	1.0	2.0	pF
Equivalent Short-Circuit Input Noise Voltage (V_{DS} = 15 Vdc, V_{GS} = 0, R_G = 1.0 MΩ, f = 100 Hz, BW = 1.0 Hz)	$\bar{e}_n$	—	20	—	nV/$\sqrt{Hz}$

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V_{DG}	25	Vdc
Reverse Gate-Source Voltage	$V_{GS(r)}$	25	Vdc
Forward Gate Current	$I_{G(f)}$	10	mAdc
Continuous Device Dissipation at or Below T_C = 25°C Linear Derating Factor	P_D	200 2.8	mW mW/°C
Storage Channel Temperature Range	T_{stg}	−65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

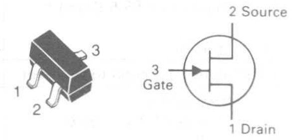
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBF5484 = 6B

MMBF5484

CASE 318-02/03, STYLE 10
SOT-23 (TO-236AA/AB)



JFET TRANSISTOR

N-CHANNEL

3

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage (I_G = −1.0 μA, V_{DS} = 0)	$V_{(BR)GSS}$	−25	—	Vdc
Gate Reverse Current (V_{GS} = −20 V, V_{DS} = 0) (V_{GS} = −20 V, V_{DS} = 0, T_A = 100°C)	I_{GSS}	 — —	 −1.0 −0.2	 nA μA
Gate Source Cutoff Voltage (V_{DS} = 15 V, I_D = 10 nA)	$V_{GS(off)}$	−0.3	−3.0	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain (V_{DS} = 15 V, V_{GS} = 0)	I_{DSS}	1.0	5.0	mAdc
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance (V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz)	$\|Y_{fs}\|$	3000	6000	μmhos
Output Admittance (V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz)	$\|Y_{os}\|$	—	50	μmhos
Input Capacitance (V_{DS} = 15 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	5.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 V, V_{GS} = 0, f = 1.0 MHz)	C_{rss}	—	1.0	pF
Output Capacitance (V_{DS} = 15 V, V_{GS} = 0, f = 1.0 MHz)	C_{oss}	—	2.0	pF
FUNCTIONAL CHARACTERISTICS				
Noise Figure (V_{DS} = 15 V, I_D = 1.0 mA, YG' = 1.0 mmhos) (R_G = 1.0 kΩ, f = 100 MHz) (V_{DS} = 15 V, V_{GS} = 0, YG' = 1.0 μmho) (R_G = 1.0 MΩ, f = 1.0 kHz)	NF	 — —	 3.0 2.5	dB
Common Source Power Gain (V_{DS} = 15 Vdc, I_D = 1.0 mAdc, f = 100 MHz)	G_{ps}	16	25	dB

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V_{DG}	25	Vdc
Reverse Gate-Source Voltage	$V_{GS(r)}$	25	Vdc
Forward Gate Current	$I_{G(f)}$	10	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ / Derate above 25°C	P_D	225 / 1.8	mW / mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ / Derate above 25°C	P_D	300 / 2.4	mW / mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

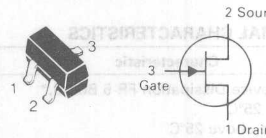
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBF5486 = 6H

MMBF5486

CASE 318-02/03, STYLE 10
SOT-23 (TO-236AA/AB)



JFET TRANSISTOR

N-CHANNEL

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage ($V_{DS} = 0$, $I_G = -1.0\ \mu A$)	$V_{(BR)GSS}$	−25	—	Vdc
Gate 1 Leakage Current ($V_{GS} = -20$ V, $V_{DS} = 0$)	I_{G1SS}	—	−1.0	nA
Gate 2 Leakage Current ($V_{GS} = -20$ V, $V_{DS} = 0$, $T_A = 100°C$)	I_{G2SS}	—	−0.2	μA
Gate Source Cutoff Voltage ($V_{DS} = 15$ V, $I_D = 10$ nA)	$V_{GS(off)}$	−2.0	−6.0	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain ($V_{GS} = 0$, $V_{DS} = 15$ V)	I_{DSS}	8.0	20	mA
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance ($V_{GS} = 0$, $V_{DS} = 15$ V, f = 1.0 kHz)	$\lvert y_{fs} \rvert$	4000	8000	μmhos
Input Admittance ($V_{GS} = 0$, $V_{DS} = 15$ V, f = 400 MHz)	$Re(y_{is})$	—	1000	μmhos
Output Admittance ($V_{GS} = 0$, $V_{DS} = 15$ V, f = 1.0 kHz)	$\lvert y_{os} \rvert$	—	75	μmhos
Output Conductance ($V_{GS} = 0$, $V_{DS} = 15$ V, f = 400 MHz)	$Re(y_{os})$	—	100	μmhos
Forward Transconductance ($V_{GS} = 0$, $V_{DS} = 15$ V, f = 400 MHz)	$Re(y_{fs})$	3500	—	μmhos
Input Capacitance ($V_{GS} = 0$, $V_{DS} = 15$ V, f = 1.0 MHz)	C_{iss}	—	5.0	pF
Reverse Transfer Capacitance ($V_{GS} = 0$, $V_{DS} = 15$ V, f = 1.0 MHz)	C_{rss}	—	1.0	pF
Output Capacitance ($V_{GS} = 0$, $V_{DS} = 15$ V, f = 1.0 MHz)	C_{oss}	—	2.0	pF
FUNCTIONAL CHARACTERISTICS				
Noise Figure	NF			dB
($V_{DS} = 15$ V, $I_D = 4.0$ mA, f = 100 MHz, $Y_G = 1.0\ \mu$mhos)		—	2.0	
($V_{DS} = 15$ V, $I_D = 4.0$ mA, $R_G = 1.0$ kΩ, f = 400 MHz, $Y_G = 1.0\ \mu$mhos)		—	4.0	
($V_{GS} = 0$, $V_{DS} = 15$ V, $R_G = 1.0$ mΩ, f = 1.0 kHz, $Y_G = 1.0\ \mu$mhos)		—	2.5	
Common Source Power Gain	G_{ps}			dB
($V_{DS} = 15$ V, $I_D = 4.0$ mA, f = 100 MHz)		18	30	
($V_{DS} = 15$ V, $I_D = 4.0$ mA, f = 400 MHz)		10	20	

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Gate-Source Voltage	V_{GS}	25	Vdc
Gate Current	I_G	10	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

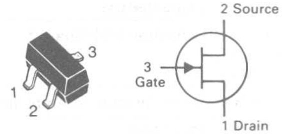
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBFJ310 = 6T

MMBFJ310

CASE 318-02/03, STYLE 10
SOT-23 (TO-236AA/AB)



JFET
VHF/UHF AMPLIFIER
TRANSISTOR

N-CHANNEL

3

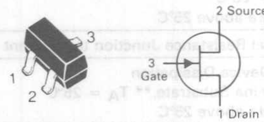
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = -1.0\ \mu Adc$, $V_{DS} = 0$)	$V_{(BR)GSS}$	−25	—	—	Vdc
Gate Reverse Current ($V_{GS} = -15$ V) ($V_{GS} = -15$ V, $T_A = 125°C$)	I_{GSS}	 — —	 — —	 −1.0 −1.0	 nAdc μAdc
Gate Source Cutoff Voltage (V_{DS} = 10 Vdc, I_D = 1.0 nAdc)	$V_{GS(off)}$	−2.0	—	−6.5	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain (V_{DS} = 10 Vdc, V_{GS} = 0)	I_{DSS}	24	—	60	mAdc
Gate-Source Forward Voltage (I_G = 1.0 mAdc, V_{DS} = 0)	$V_{GS(f)}$	—	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance (V_{DS} = 10 Vdc, I_D = 10 mAdc, f = 1.0 kHz)	$\|Y_{fs}\|$	8.0	—	18	mmhos
Output Admittance (V_{DS} = 10 Vdc, I_D = 10 mAdc, f = 1.0 kHz)	$\|Y_{os}\|$	—	—	200	μmhos
Input Capacitance ($V_{GS} = -10$ Vdc, V_{DS} = 0 Vdc, f = 1.0 MHz)	C_{iss}	—	—	5.0	pF
Reverse Transfer Capacitance ($V_{GS} = -10$ Vdc, V_{DS} = 0 Vdc, f = 1.0 MHz)	C_{rss}	—	—	2.5	pF
Equivalent Short-Circuit Input Noise Voltage (V_{DS} = 10 Vdc, I_D = 10 mAdc, f = 100 Hz)	$\bar{e}_n$	—	10	—	$nV/\sqrt{Hz}$

Drain-Source Voltage	V_{DS}	25	Vdc
Gate-Source Voltage	V_{GS}	25	Vdc
Gate Current	I_G	10	mAdc

MMBFU310

CASE 318-02/03, STYLE 10
SOT-23 (TO-236AA/AB)



JFET TRANSISTOR

N-CHANNEL

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

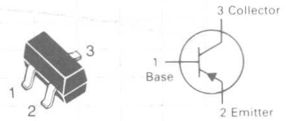
MMBFU310 = 6C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage ($I_G = -1.0\ \mu A$, $V_{DS} = 0$)	$V_{(BR)GSS}$	−25		Vdc
Gate 1 Leakage Current ($V_{GS} = -15$ V, $V_{DS} = 0$)	I_{G1SS}	–	−150	pA
Gate 2 Leakage Current ($V_{GS} = -15$ V, $V_{DS} = 0$, $T_A = 125°C$)	I_{G2SS}	—	−150	nA
Gate Source Cutoff Voltage ($V_{DS} = 10$ V, $I_D = 1.0$ nA)	$V_{GS(off)}$	−2.5	−6.0	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain ($V_{DS} = 10$ V, $V_{GS} = 0$)	I_{DSS}	24	60	mA
Gate-Source Forward Voltage ($I_G = 10$ mA, $V_{DS} = 0$)	$V_{GS(f)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance ($V_{DS} = 10$ V, $I_D = 10$ mA, f = 1.0 kHz)	$\|Y_{fs}\|$	10	18	mmhos
Output Admittance ($V_{DS} = 10$ V, $I_D = 10$ mA, f = 1.0 kHz)	$\|y_{os}\|$	—	150	μmhos
Input Capacitance ($V_{GS} = -10$ V, $V_{DS} = 10$ V, f = 1.0 MHz)	C_{iss}	—	5.0	pF
Reverse Transfer Capacitance ($V_{GS} = -10$ V, $V_{DS} = 10$ V, f = 1.0 MHz)	C_{rss}	—	2.5	pF

Collector-Base Voltage	V_{CBO}	15	Vdc
Emitter-Base Voltage	V_{EBO}	4.5	Vdc
Collector Current — Continuous	I_C	30	mA

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



HIGH FREQUENCY TRANSISTOR

PNP SILICON

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBR536 = 7R

ELECTRICAL CHARACTERISTICS (T_C = 25°C *For both package types unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 2.0 mA, I_B = 0)	$V_{(BR)CEO}$	10	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μA, I_E = 0)	$V_{(BR)CBO}$	15	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μA, I_C = 0)	$V_{(BR)EBO}$	4.5	—	—	Vdc
Collector Cutoff Current (V_{CB} = 10 Vdc, I_E = 0)	I_{CBO}	—	—	10	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 20 mA, V_{CE} = 5.0 V)	h_{FE}	20	—	200	—
DYNAMIC CHARACTERISTICS					
Current Gain-Bandwidth Product (I_C = 20 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 GHz)	f_T	—	5.5	—	GHz
Collector-Base Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	—	0.8	1.2	pF
FUNCTIONAL TESTS					
Gain @ Noise Figure (I_C = 10 mAdc, V_{CE} = 5.0 Vdc) f = 500 MHz f = 1.0 GHz	G_{NF}	— —	14 8.0	— —	dB
Noise Figure (I_C = 10 mAdc, V_{CE} = 5.0 Vdc) f = 500 MHz f = 1.0 GHz	NF	— —	4.5 6.0	— —	dB

3

3

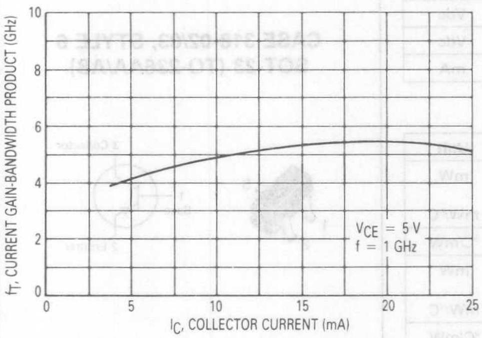


Figure 1. Current Gain-Bandwidth Product versus Collector Current

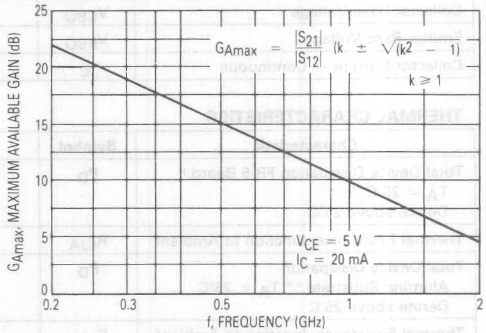


Figure 2. Maximum Available Gain (G_{Amax}) versus Frequency

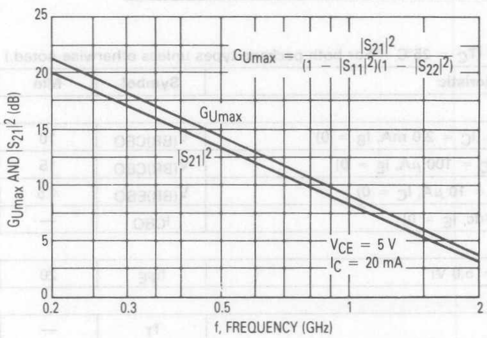


Figure 3. Maximum Unilateral Gain (G_{Umax}) and Insertion Gain ($|S_{21}|^2$) versus Frequency

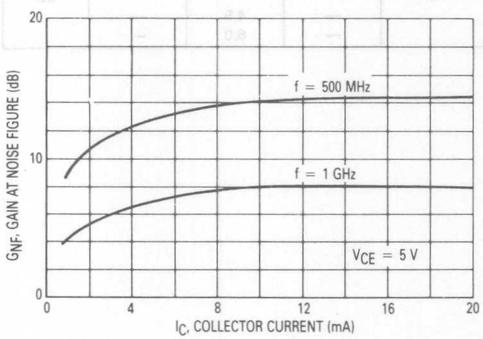


Figure 4. Gain at Noise Figure versus Collector Current

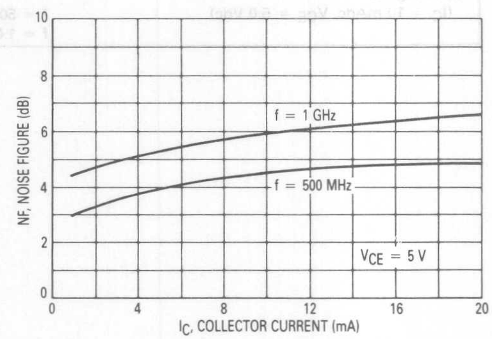


Figure 5. Noise Figure versus Collector Current

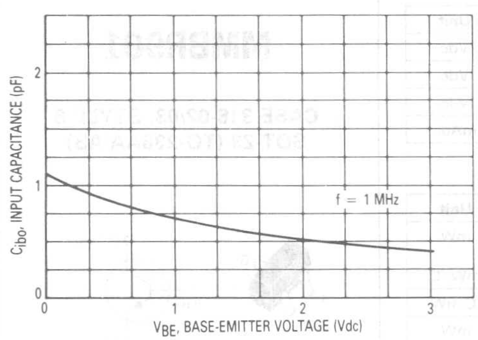


Figure 6. Input Capacitance versus Emitter-Base Voltage

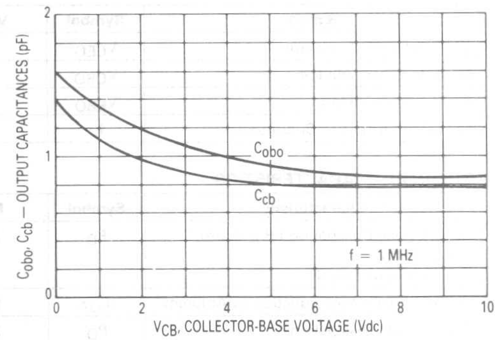
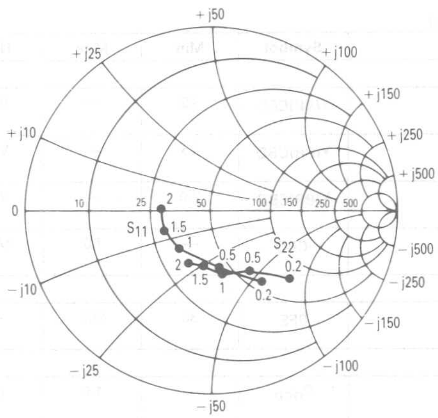
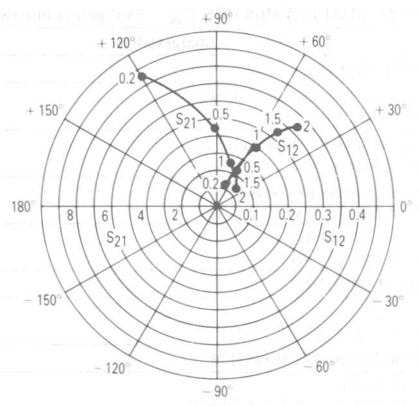


Figure 7. Output Capacitance versus Collector-Base Voltage

INPUT/OUTPUT REFLECTION COEFFICIENTS versus FREQUENCY V_{CE} = 10 V, I_C = 10 mA



FORWARD AND REVERSE TRANSMISSION COEFFICIENTS versus FREQUENCY V_{CE} = 10 V, I_C = 10 mA

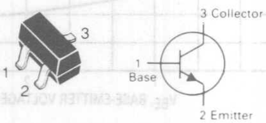


COMMON EMITTER S-PARAMETERS

V_{CE} (Volts)	I_C (mA)	f (MHz)	S_{11}		S_{21}		S_{12}		S_{22}	
			$\|S_{11}\|$	$\angle\phi$	$\|S_{21}\|$	$\angle\phi$	$\|S_{12}\|$	$\angle\phi$	$\|S_{22}\|$	$\angle\phi$
10	5	200	0.60	−44	6.47	126	0.07	66	0.68	−35
		500	0.37	−70	3.57	97	0.14	60	0.48	−50
		1000	0.27	−105	2.16	74	0.22	53	0.40	−69
		1500	0.24	−138	1.62	58	0.29	46	0.37	−87
		2000	0.22	−166	1.38	44	0.33	42	0.34	−103
	10	200	0.48	−54	8.65	120	0.06	66	0.58	−40
		500	0.30	−82	4.32	94	0.12	62	0.38	−58
		1000	0.24	−122	2.52	74	0.20	57	0.32	−78
		1500	0.24	−155	1.84	59	0.27	51	0.30	−96
		2000	0.24	178	1.54	46	0.32	47	0.28	−112
	20	200	0.39	−63	10.10	115	0.06	67	0.49	−50
		500	0.25	−94	4.77	91	0.11	65	0.32	−65
		1000	0.24	−136	2.72	73	0.19	60	0.27	−84
		1500	0.24	−167	1.96	58	0.26	54	0.26	−102
		2000	0.26	168	1.63	46	0.32	50	0.25	−119

MMBR901

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



RF AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Base Voltage	V_{CBO}	25	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	30	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBR901 = 7A

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	15	—	Vdc
Collector-Base Breakdown Voltage (I_C = 0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	25	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 0.1 mAdc, I_C = 0)	$V_{(BR)EBO}$	2.0	—	Vdc
Collector Cutoff Current (V_{CB} = 15 Vdc, I_E = 0)	I_{CBO}	—	50	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 5.0 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}	30	200	—
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	1.0	pF
Common-Emitter Amplifier Power Gain (V_{CC} = 6.0 Vdc, I_C = 5.0 mAdc, f = 1.0 GHz)	G_{pe}(1)	16 (Typ)	—	dB
Noise Figure (I_C = 5.0 mAdc, V_{CE} = 6.0 Vdc, f = 1.0 GHz)	NF(1)	—	1.9 (Typ)	dB

(1) Noise figure and power gain measured on the Ailtech 7380 50Ω system.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Base Voltage	V_{CBO}	20	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	35	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

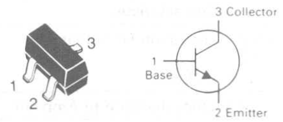
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBR920 = 7B

MMBR920

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



RF AMPLIFIER/SWITCHING TRANSISTOR

NPN SILICON

3

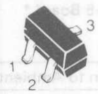
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

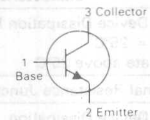
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	15	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.1$ mAdc, $I_E = 0$)	$V_{(BR)CBO}$	20	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 0.1$ mAdc, $I_C = 0$)	$V_{(BR)EBO}$	2.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 10$ Vdc, $I_E = 0$)	I_{CBO}	—	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 14$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	25	—	250	—
SMALL SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 14$ mAdc, $V_{CE} = 10$ Vdc, f = 0.5 GHz)	f_T	—	4.5	—	GHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{cb}	—	—	1.0	pF
Noise Figure ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc, f = 0.5 GHz) ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 GHz)	NF(1)	 — —	 2.4 3.0	 — —	dB
Common-Emitter Amplifier Power Gain ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc, f = 0.5 GHz) ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 GHz)	G_{pe}(1)	 — —	 15 10	 — —	dB

(1) Noise figure and power gain measured on the Ailtech 7380 50 Ω system.

MMBR930

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)





AMPLIFIER/SWITCHING TRANSISTOR

NPN SILICON

3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	12	Vdc
Collector-Base Voltage	V_{CBO}	15	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	35	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBR930 = 7C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	12	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	15	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 0.1 mAdc, I_C = 0)	$V_{(BR)EBO}$	3.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 5.0 Vdc, I_E = 0)	I_{CBO}	—	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 30 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}	25	—	250	—
SMALL-SIGNAL CHARACTERISTICS					
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	—	—	1.0	pF
Noise Figure	NF(1)				dB
(I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc, f = 0.5 GHz)		—	1.9	—	
(I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 GHz)		—	2.5	—	
Common-Emitter Amplifier Power Gain	G_{pe}(1)				dB
(I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc, f = 0.5 GHz)		—	11	—	
(I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc, f = 0.5 GHz)		—	8.0	—	

(1) Noise figure and power gain measured on the Ailtech 7380 50 Ω system.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	5.0	Vdc
Collector-Base Voltage	V_{CBO}	10	Vdc
Emitter-Base Voltage	V_{EBO}	2.0	Vdc
Collector Current — Continuous	I_C	5.0	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

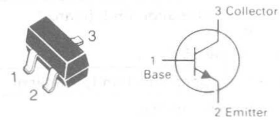
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBR931 = 7D

MMBR931

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



RF AMPLIFIER TRANSISTOR

NPN SILICON

3

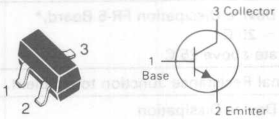
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 0.1$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	5.0	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.01$ mAdc, $I_E = 0$)	$V_{(BR)CBO}$	10	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 0.1$ mAdc, $I_C = 0$)	$V_{(BR)EBO}$	2.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 5.0$ Vdc, $I_E = 0$)	I_{CBO}	—	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 0.25$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	30	—	150	—
SMALL-SIGNAL CHARACTERISTICS					
Collector-Base Capacitance ($V_{CB} = 1.0$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{cb}	—	—	0.5	pF
Noise Figure ($I_E = 0.25$ mAdc, $V_{CE} = 1.0$ Vdc, f = 1 0 GHz)	NF(1)	—	4.3	—	dB
Gate Power Dissipation ($I_E = 0.25$ mAdc, $V_{CE} = 1.0$ Vdc, f = 1.0 GHz)	PG(1)	—	10	—	—

(1) Noise figure and power gain measured on the Ailtech 7380 50 Ω system.

MMBR2060

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



RF AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	14	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	50	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBR2060 = 7E

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	14		Vdc
Collector Cutoff Current ($V_{CB} = 10$ Vdc, $I_E = 0$)	I_{CBO}	—	50	nAdc
Emitter Cutoff Current ($V_{EB} = 4.0$, $I_C = 0$)	I_{EBO}	—	100	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 5.0$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 20$ mAdc, $V_{CE} = 10$ Vdc, f = 500 MHz)	h_{FE}	 20 2.0	— — —	
Collector-Emitter Saturation Voltage ($I_C = 80$ mAdc, $I_B = 8.0$ mAdc)	$V_{CE(sat)}$	—	0.38	Vdc
Base-Emitter Saturation Voltage ($I_C = 40$ mAdc, $I_B = 20$ mAdc)	$V_{BE(sat)}$	—	0.98	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 20$ mAdc, $V_{CE} = 1.0$ Vdc, f = 100 MHz)	f_T	—	1.0	GHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$)	C_{cb}	—	1.0	pF
Emitter-Base Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$)	C_{eb}	—	3.0	pF
Noise Figure ($V_{CE} = 10$ Vdc, $I_E = 1.5$ mAdc, f = 450 MHz)	NF(1)	—	3.5	dB
Common-Emitter Amplifier Power Gain ($V_{CE} = 10$ Vdc, $I_E = 1.5$ mAdc, f = 450 Mhz)	G_{pe}(1)	12.5	—	dB

(1) Noise figure and power gain measured on the Ailtech 7380 50 Ω system.

Emitter-Base Voltage	V_{EBO}	2.5	Vdc
Collector Current — Continuous	I_C	40	mAdc

THERMAL CHARACTERISTICS

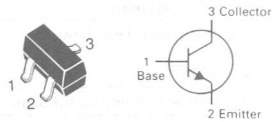
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBR2857 = 7K

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



RF TRANSISTOR

NPN SILICON

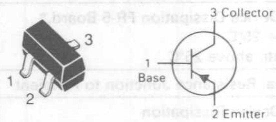
3

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 3.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	15	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 1.0$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	30	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	2.5	—	Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_E = 0$)	I_{CBO}	—	0.05	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 3.0$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	30	—	—
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	1000	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 0.1 MHz)	C_{cb}	—	1.0	pF
Small-Signal Current Gain ($I_C = 2.0$ mAdc, $V_{CE} = 6.0$ Vdc, f = 1.0 kHz)	h_{fe}	50	—	—
Noise Figure ($I_C = 1.5$ mAdc, $V_{CE} = 6.0$ Vdc, $R_S = 50\ \Omega$, f = 450 MHz)	NF	—	4.5	dB
Common-Emitter Amplifier Power Gain ($I_C = 1.5$ mAdc, $V_{CE} = 6.0$ Vdc, f = 450 MHz)	G_{PE}	12.5	—	dB

MMBR4957

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



RF AMPLIFIER TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	30	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBR4957 = 7F

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	30	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	30		Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	3.0		Vdc
Collector Cutoff Current (V_{CB} = 10 Vdc, I_C = 0)	I_{CBO}	—	0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 2.0 mAdc, V_{CE} = 10 Vdc)	h_{FE}	20	150	—
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_E = 2.0 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	1,200	—	MHz
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	—	0.8	pF
Common-Emitter Amplifier Power Gain(1) (V_{CE} = 10 Vdc, I_C = 2.0 mAdc, f = 450 MHz)	G_{pe}	17 (Typ)	—	dB
Noise Figure(1) (I_C = 2.0 mAdc, V_{CE} = 10 Vdc, f = 450 MHz)	NF	—	3.0 (Typ)	dB

(1) Noise figure and power gain measured on the Ailtech 7380 50 Ω system.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	10	Vdc
Collector-Base Voltage	V_{CBO}	15	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	20	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

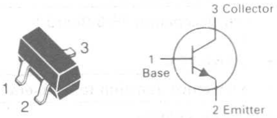
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBR5031 = 7G

MMBR5031

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



RF AMPLIFIER TRANSISTOR

NPN SILICON

3

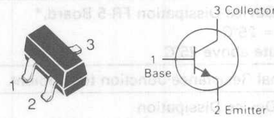
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	10	—	Vdc
Collector-Base Breakdown Voltage (I_C = 0.01 mAdc, I_E = 0)	$V_{(BR)CBO}$	15	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 0.01 mAdc, I_C = 0)	$V_{(BR)EBO}$	3.0	—	Vdc
Collector Cutoff Current (V_{CB} = 6.0 Vdc, I_E = 0)	I_{CBO}	—	10	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 6.0 Vdc)	h_{FE}	25	300	—
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 5.0 mAdc, V_{CE} = 6.0 Vdc, f = 100 MHz)	f_T	1,000	—	MHz
Collector-Base Capacitance (V_{CE} = 6.0 Vdc, I_E = 0, f = 0.1 MHz)	C_{cb}	—	1.5	pF
Noise Figure (I_C = 1.0 mAdc, V_{CE} = 6.0 Vdc, f = 450 MHz)	NF(1)	—	2.5	dB
Common-Emitter Amplifier Power Gain (I_C = 1.0 mAdc, V_{CE} = 6.0 Vdc, f = 450 MHz)	G_{pe}(1)	14	25	dB

(1) Noise figure and power gain measure on Ailtech 7380 50 Ω system.

MMBR5179

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



RF AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	12	Vdc
Collector-Base Voltage	V_{CBO}	20	Vdc
Emitter-Base Voltage	V_{EBO}	2.5	Vdc
Collector Current — Continuous	I_C	50	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBR5179 = 7H

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 3.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	12	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.01$ mAdc, $I_E = 0$)	$V_{(BR)CBO}$	20	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 0.01$ mAdc, $I_C = 0$)	$V_{(BR)EBO}$	2.5	—	Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_E = 0$)	I_{CBO}	—	0.02	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 3.0$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	25	—	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	0.4	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	—	1.0	Vdc
SMALL SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 5.0$ mAdc, $V_{CE} = 6.0$ Vdc, f = 100 MHz)	f_T	900	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 0.1 to 1.0 MHz)	C_{cb}	—	1.0	pF
Small Signal Current Gain ($I_C = 2.0$ mAdc, $V_{CE} = 6.0$ Vdc, f = 1.0 kHz)	h_{fe}	25	—	—
Noise Figure ($I_C = 1.5$ mAdc, $V_{CE} = 6.0$ Vdc, $R_S = 50\ \Omega$, f = 200 Mhz)	NF(1)	—	4.5	dB
Common-Emitter Amplifier Power Gain ($V_{CE} = 6.0$ Vdc, $I_C = 5.0$ mAdc, f = 200 MHz)	G_{pe}(1)	15	—	dB

(1) Noise figure and power gain measured on the Ailtech 7380 50 Ω system.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Forward Current Avg. (T_C = +67°C)	I_F	510	mA
Peak Forward Gate Voltage	V_{GFM}	5.0	V
Peak Forward Blocking Voltage RG = 1.0 k MMBS5060 MMBS5061 MMBS5062	V_{FXM}	 30 60 100	V

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

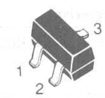
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

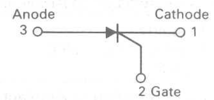
DEVICE MARKING

MMBS5060 = 5R; MMBS5061 = 5S; MMBS5062 = 5T

MMBS5060
MMBS5061
MMBS5062

CASE 318-02/03, STYLE 14
SOT-23 (TO-236AA/AB)





SILICON CONTROLLED RECTIFIER

PNPN DEVICE

3

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate Trigger Voltage (R_L = 100 Ω, R_{GC} = 1.0 kΩ, T_C = 125°C)	MMBS5060 = 30 V Anode Voltage = MMBS5061 = 60 V MMBS5062 = 100 V	V_{GNT}	0.1	—	V
Peak Forward Blocking Current (R_{GC} = 1.0 kΩ, T_C = 125°C)	MMBS5060 = 30 V V_{FXM} = MMBS5061 = 60 V MMBS5062 = 100 V	I_{FXM}	—	50	μA
Peak Reverse Blocking Current (R_{GC} = 1.0 kΩ, T_C = 125°C)	MMBS5060 = 30 V V_{RXM} = MMBS5061 = 60 V MMBS5062 = 100 V	I_{RXM}	—	50	μA
Forward Voltage* (I_F = 1.2 A Peak)		V_F	—	1.7	V
Gate Trigger Current** (R_{GC} = 1.0 kΩ, V_{AC} = 7.0 V, R_L = 100 Ω		I_{GT}	—	200	μA
Gate Trigger Voltage (R_{GC} = 1.0 kΩ, V_{AC} = 7.0 V, R_L = 100 Ω		V_{GT}	—	0.8	V
Holding Current (V_{AC} = 7.0 V, R_{GC} = 1.0 kΩ		I_H	—	5.0	mA

*PW ≤ 1.0 ms, D.C. ≤ 1.0%.
**RGC current not included in measurement.

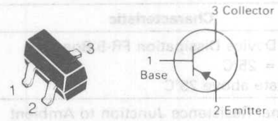
3

MAXIMUM RATINGS

Rating	Symbol	Value 404	Value 404A	Unit
Collector-Emitter Voltage	V_{CEO}	24	35	Vdc
Collector-Base Voltage	V_{CBO}	25	40	Vdc
Emitter-Base Voltage	V_{EBO}	12	25	Vdc
Collector Current — Continuous	I_C	150		mAdc

MMBT404
MMBT404A

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



CHOPPER TRANSISTOR

PNP SILICON

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

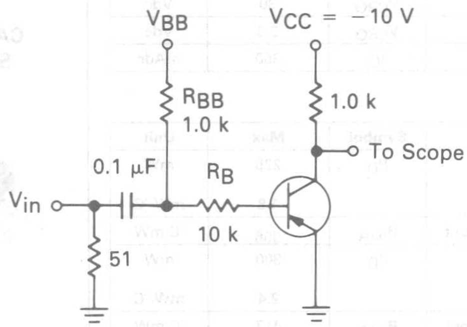
DEVICE MARKING

MMBT404 = 2M; MMBT404A = 2N

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	MMBT404 MMBT404A	$V_{(BR)CEO}$	24 35	— —	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	MMBT404 MMBT404A	$V_{(BR)CBO}$	25 40	— —	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	MMBT404 MMBT404A	$V_{(BR)EBO}$	12 25	— —	— —	Vdc
Collector Cutoff Current (V_{CB} = 10 Vdc, I_E = 0)		I_{CBO}	—	—	100	nAdc
Emitter Cutoff Current (V_{BE} = 10 Vdc, I_C = 0)		I_{EBO}	—	—	100	nAdc
ON CHARACTERISTICS						
DC Current Gain (I_C = 12 mAdc, V_{CE} = 0.15 Vdc)		h_{FE}	30	—	400	—
Collector-Emitter Saturation Voltage (I_C = 12 mAdc, I_B = 0.4 mAdc) (I_C = 24 mAdc, I_B = 1.0 mAdc)		$V_{CE(sat)}$	— —	— —	0.15 0.20	Vdc
Base-Emitter Saturation Voltage (I_C = 12 mAdc, I_B = 0.4 mAdc) (I_C = 24 mAdc, I_B = 1.0 mAdc)		$V_{BE(sat)}$	— —	— —	0.85 1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Output Capacitance (V_{CB} = 6.0 Vdc, I_E = 0)		C_{obo}	—	—	20	pF
SWITCHING CHARACTERISTICS						
Delay Time (V_{CC} = 10 Vdc, I_C = 10 mAdc) (Figure 1)		t_d	—	43	—	ns
Rise Time (I_{B1} = 1.0 mAdc, $V_{BE(off)}$ = 14 Vdc)		t_r	—	180	—	ns
Storage Time (V_{CC} = 10 Vdc, I_C = 10 mAdc)		t_s	—	675	—	ns
Fall Time (I_{B1} = I_{B2} = 1.0 mAdc) (Figure 1)		t_f	—	160	—	ns

FIGURE 1 — SWITCHING TIME TEST CIRCUIT

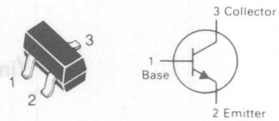


	V_{in} (Volts)	V_{BB} (Volts)
t_{on}, t_d, t_r	− 12	+ 1.4
t_{off}, t_s and t_f	+ 20.6	− 11.6

Voltages and resistor values shown are for $I_C = 10$ mA, $I_C/I_B = 10$ and $I_{B1} = I_{B2}$

MMBT918

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



VHF/UHF TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	350	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

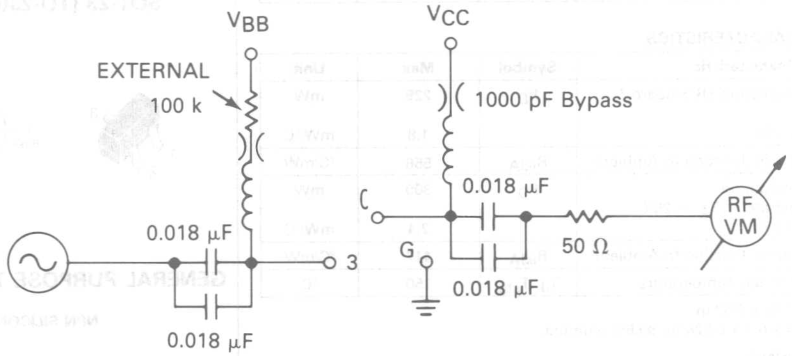
DEVICE MARKING

MMBT918 = 3B

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 3.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	15	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 1.0$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	30	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_E = 0$)	I_{CBO}	—	50	nAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 3.0$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	20	—	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	0.4	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	600	—	MHz
Output Capacitance ($V_{CB} = 0$ Vdc, $I_E = 0$, f = 1.0 MHz) ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{obo}	 — —	 3.0 1.7	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)	C_{ibo}	—	2.0	pF
Noise Figure ($I_C = 1.0$ mAdc, $V_{CE} = 6.0$ Vdc, $R_S = 50\ \Omega$, f = 60 MHz) (Figure 1)	NF	—	6.0	dB
Power Output ($I_C = 8.0$ mAdc, $V_{CB} = 15$ Vdc, f = 500 MHz)	P_{out}	30	—	mW
Common-Emitter Amplifier Power Gain ($I_C = 6.0$ mAdc, $V_{CB} = 12$ Vdc, f = 200 MHz)	G_{pe}	11	—	dB

FIGURE 1 — NF, Gpe MEASUREMENT CIRCUIT 20-200



NF Test Conditions

$I_C = 1.0$ Amp
$V_{CE} = 6.0$ Volts
$R_S = 50\ \Omega$
f = 60 MHz

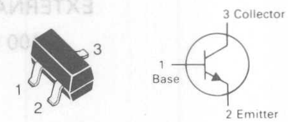
Gpe Test Conditions

$I_C = 6.0$ mA
$V_{CE} = 12$ Volts
f = 200 MHz

3

MMBT930

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to MPS3904 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	45	Vdc
Collector-Base Voltage	V_{CBO}	45	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	30	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT930 = 1X

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	45	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	45	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CE} = 5.0 Vdc, I_B = 0)	I_{CEO}	—	10	nAdc
Collector Cutoff Current (V_{CB} = 45 Vdc, I_E = 0)	I_{CBO}	—	10	nAdc
Collector Cutoff Current (V_{CE} = 45 Vdc, V_{BE} = 0)	I_{CES}	—	10	nAdc
Emitter Cutoff Current (V_{EB} = 5.0 Vdc, I_C = 0)	I_{EBO}	—	10	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 10 μAdc, V_{CE} = 5.0 Vdc) (I_C = 500 μAdc, V_{CE} = 5.0 Vdc) (I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}	 100 150 —	 300 — 600	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.5 mAdc)	$V_{CE(sat)}$	—	1.0	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.5 mAdc)	$V_{BE(sat)}$	0.6	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 500 μAdc, V_{CE} = 5.0 Vdc, f = 30 MHz)	f_T	30	—	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	8.0	pF
Noise Figure (I_C = 10 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 kΩ, f = 10 Hz to 15.7 kHz)	NF	—	3.0	dB

MAXIMUM RATINGS

Rating	Symbol	MMBT2222	MMBT2222A	Unit
Collector-Emitter Voltage	V_{CEO}	30	40	Vdc
Collector-Base Voltage	V_{CBO}	60	75	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	6.0	Vdc
Collector Current — Continuous	I_C	600		mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

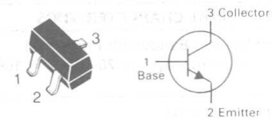
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT2222 = 1B; MMBT2222A = 1P

MMBT2222
MMBT2222A

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



TRANSISTOR

NPN SILICON

3

Refer to MPS2222 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 10$ mAdc, $I_B = 0$)	MMBT2222	$V_{(BR)CEO}$	30	—	Vdc
	MMBT2222A		40	—	
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	MMBT2222	$V_{(BR)CBO}$	60	—	Vdc
	MMBT2222A		75	—	
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	MMBT2222	$V_{(BR)EBO}$	5.0	—	Vdc
	MMBT2222A		6.0	—	
Collector Cutoff Current ($V_{CE} = 60$ Vdc, $V_{EB(off)} = 3.0$ Vdc)	MMBT2222A	I_{CEX}	—	10	nAdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$)	MMBT2222	I_{CBO}	—	0.01	μAdc
($V_{CB} = 60$ Vdc, $I_E = 0$)	MMBT2222A		—	0.01	
($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = 125°C$)	MMBT2222		—	10	
($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = 125°C$)	MMBT2222A		—	10	
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)	MMBT2222A	I_{EBO}	—	10	nAdc
Base Cutoff Current ($V_{CE} = 60$ Vdc, $V_{EB(off)} = 3.0$ Vdc)	MMBT2222A	I_{BL}	—	20	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 10$ Vdc)		h_{FE}	35	—	—
($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc)			50	—	
($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc)			75	—	
($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, $T_A = -55°C$)	MMBT2222A only		35	—	
($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)(1)			100	300	
($I_C = 150$ mAdc, $V_{CE} = 1.0$ Vdc)(1)			50	—	
($I_C = 500$ mAdc, $V_{CE} = 10$ Vdc)(1)	MMBT2222		30	—	
	MMBT2222A		40	—	
Collector-Emitter Saturation Voltage(1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	MMBT2222	$V_{CE(sat)}$	—	0.4	Vdc
	MMBT2222A		—	0.3	
($I_C = 500$ mAdc, $I_B = 50$ mAdc)	MMBT2222		—	1.6	
	MMBT2222A		—	1.0	

3

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Base-Emitter Saturation Voltage(1)		$V_{BE(sat)}$			Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)	MMBT2222		—	1.3	
	MMBT2222A		0.6	1.2	
(I_C = 500 mAdc, I_B = 50 mAdc)	MMBT2222		—	2.6	
	MMBT2222A		—	2.0	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2)		f_T			MHz
(I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	MMBT2222		250	—	
	MMBT2222A		300	—	
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	8.0	pF
Input Capacitance		C_{ibo}			pF
(V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	MMBT2222		—	30	
	MMBT2222A		—	25	
Input Impedance		h_{ie}			kΩ
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MMBT2222A		2.0	8.0	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MMBT2222A		0.25	1.25	
Voltage Feedback Ratio		h_{re}			X 10^{-4}
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MMBT2222A		—	8.0	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MMBT2222A		—	4.0	
Small-Signal Current Gain		h_{fe}			—
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MMBT2222A		50	300	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MMBT2222A		75	375	
Output Admittance		h_{oe}			μmhos
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MMBT2222A		5.0	35	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MMBT2222A		25	200	
Collector Base Time Constant (I_E = 20 mAdc, V_{CB} = 20 Vdc, f = 31.8 MHz)	MMBT2222A	$rb'C_c$		150	ps
Noise Figure (I_C = 100 μAdc, V_{CE} = 10 Vdc, R_S = 1.0 kΩ, f = 1.0 kHz)	MMBT2222A	NF	4.0	4.0	dB

SWITCHING CHARACTERISTICS MMBT2222A only

		Symbol	Min	Max	Unit
Delay Time	(V_{CC} = 30 Vdc, $V_{BE(off)}$ = 0.5 Vdc,	t_d	—	10	ns
Rise Time	I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_r	—	25	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc,	t_s	—	225	ns
Fall Time	I_{B1} = I_{B2} = 15 mAdc)	t_f	—	60	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Emitter Voltage	V_{CES}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4.5	Vdc
Collector Current — Continuous	I_C	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

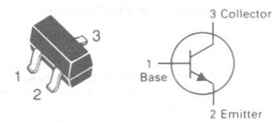
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT2369 = 1J

MMBT2369

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



SWITCHING TRANSISTOR

NPN SILICON

Refer to MPS2369 for graphs.

3

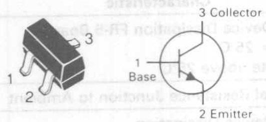
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	15	—	—	Vdc
Collector-Emitter Breakdown Voltage (I_C = 10 μAdc, V_{BE} = 0)	$V_{(BR)CES}$	40	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	4.5	—	—	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0) (V_{CB} = 20 Vdc, I_E = 0, T_A = 125°C)	I_{CBO}	 — —	 — —	 0.4 30	μAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc, T_A = −55°C) (I_C = 100 mAdc, V_{CE} = 2.0 Vdc)	h_{FE}	 40 20 20	 — — —	 120 — —	—
Collector-Emitter Saturation Voltage(1) (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{CE(sat)}$	—	—	0.25	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{BE(sat)}$	0.70	—	0.85	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	—	4.0	pF
Small Signal Current Gain (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	h_{fe}	5.0	—	—	—
SWITCHING CHARACTERISTICS					
Storage Time (I_{B1} = I_{B2} = I_C = 10 mAdc)	t_s	—	5.0	13	ns
Turn-On Time (V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = 3.0 mAdc)	t_{on}	—	8.0	12	ns
Turn-Off Time (V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = 3.0 mAdc, I_{B2} = 1.5 mAdc)	t_{off}	—	10	18	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MMBT2484

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



LOW NOISE TRANSISTOR

NPN SILICON

Refer to MPSA18 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	60	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	50	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT2484 = 1U

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	60	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 45 Vdc, I_E = 0) (V_{CB} = 45 Vdc, I_E = 0, T_A 150°C)	I_{CBO}	 — —	 10 10	 nAdc μAdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)	I_{EBO}	—	10	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc) (I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}	 250 	 — 800	
Collector-Emitter Saturation Voltage (I_C = 1.0 mAdc, I_B = 0.1 mAdc)	$V_{CE(sat)}$	—	0.35	Vdc
Base-Emitter On Voltage (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	$V_{BE(on)}$	—	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1 MHz)	C_{obo}	—	6.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1 MHz)	C_{ibo}	—	6.0	pF
Noise Figure (I_C = 10 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	—	3.0	dB

MAXIMUM RATINGS

Rating	Symbol	MPS2907	MPS2907A	Unit
Collector-Emitter Voltage	V_{CEO}	40	60	Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	600		mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

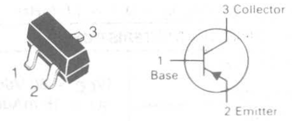
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT2907 = 2B; MMBT2907A = 2F

MMBT2907
MMBT2907A

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

Refer to MPS2907 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	MMBT2907 MMBT2907A	$V_{(BR)CEO}$	40 60	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CE} = 30 Vdc, $V_{BE(off)}$ = 0.5 Vdc)		I_{CEX}	—	50	nAdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0)	MMBT2907 MMBT2907A	I_{CBO}	— —	0.020 0.010	μAdc
(V_{CB} = 50 Vdc, I_E = 0, T_A = 125°C)	MMBT2907 MMBT2907A		— —	20 10	
Base Current (V_{CE} = 30 Vdc, $V_{BE(off)}$ = 0.5 Vdc)		I_B	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 0.1 mAdc, V_{CE} = 10 Vdc)	MMBT2907 MMBT2907A	h_{FE}	35 75	— —	—
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)	MMBT2907 MMBT2907A		50 100	— —	
(I_C = 10 mAdc, V_{CE} = 10 Vdc)	MMBT2907 MMBT2907A		75 100	— —	
(I_C = 150 mAdc, V_{CE} = 10 Vdc)(1)	MMBT2907, MMBT2907A		100	300	
(I_C = 500 mAdc, V_{CE} = 10 Vdc)(1)	MMBT2907 MMBT2907A		30 50	— —	
Collector-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)		$V_{CE(sat)}$	— —	0.4 1.6	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)		$V_{BE(sat)}$	— —	1.3 2.6	Vdc

3

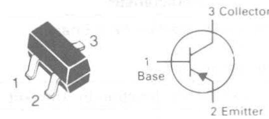
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(1),(2) (I_C = 50 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)		f_T	200	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	8.0	pF
Input Capacitance (V_{BE} = 2.0 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	30	pF
SWITCHING CHARACTERISTICS					
Turn-On Time		t_{on}	—	45	ns
Delay Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_d	—	10	ns
Rise Time		t_r	—	40	ns
Turn-Off Time		t_{off}	—	100	ns
Storage Time	(V_{CC} = 6.0 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_s	—	80	ns
Fall Time		t_f	—	30	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

MMBT3640

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



SWITCHING TRANSISTOR

PNP SILICON

3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	12	Vdc
Collector-Base Voltage	V_{CBO}	12	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	80	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT3640 = 2J

Refer to MPS3640 for graphs.

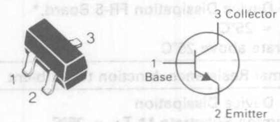
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 100 μAdc, V_{BE} = 0)	$V_{(BR)CES}$	12	—	Vdc
Collector-Emitter Sustaining Voltage(1) (I_C = 10 mAdc, I_B = 0)	$V_{CEO(sus)}$	12	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	12	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current (V_{CE} = 6.0 Vdc, V_{BE} = 0) (V_{CE} = 6.0 Vdc, V_{BE} = 0, T_A = 65°C)	I_{CES}	— —	0.01 1.0	μAdc
Base Current (V_{CE} = 6.0 Vdc, V_{BE} = 0)	I_B	—	10	nAdc
ON CHARACTERISTICS(1)				
DC Current Gain (I_C = 10 mAdc, V_{CE} = 0.3 Vdc) (I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	h_{FE}	30 20	120 —	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc) (I_C = 10 mAdc, I_B = 1.0 mAdc, T_A = 65°C)	$V_{CE(sat)}$	— — —	0.2 0.6 0.25	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.5 mAdc) (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)	$V_{BE(sat)}$	0.75 0.8 —	0.95 1.0 1.5	Vdc
SMALL SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)	f_T	500	—	MHz
Output Capacitance (V_{CB} = = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	3.5	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	—	3.5	pF
SWITCHING CHARACTERISTICS				
Delay Time — (V_{CC} = 6.0 Vdc, I_C = 50 mAdc, $V_{BE(off)}$ = 1.9 Vdc, I_{B1} = 5.0 mAdc)	t_d	—	10	ns
Rise Time — (V_{CC} = 6.0 Vdc, I_C = 50 mAdc, $V_{BE(off)}$ = 1.9 Vdc, I_{B1} = 5.0 mAdc)	t_r	—	30	ns
Storage Time — (V_{CC} = 6.0 Vdc, I_C = 50 mAdc, I_{B1} = I_{B2} = 5.0 mAdc)	t_s	—	20	ns
Fall Time — (V_{CC} = 6.0 Vdc, I_C = 50 mAdc, I_{B1} = I_{B2} = 5.0 mAdc)	t_f	—	12	ns
Turn-On Time (V_{CC} = 6.0 Vdc, I_C = 50 mAdc, $V_{BE(off)}$ = 1.9 Vdc, I_{B1} = 5.0 mAdc) (V_{CC} = 1.5 Vdc, I_C = 10 mAdc, I_{B1} = 0.5 mAdc)	t_{on}	— —	25 60	ns
Turn-Off Time (V_{CC} = 6.0 Vdc, I_C = 50 mAdc, $V_{BE(off)}$ = 1.9 V, I_{B1} = I_{B2} = 5.0 mAdc) (V_{CC} = 1.5 Vdc, I_C = 10 mAdc, I_{B1} = I_{B2} = 0.5 mAdc)	t_{off}	— —	35 75	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MMBT3903
MMBT3904

CASE 318-03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N3903 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT3903 = 1Y; MMBT3904 = 1A

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)		$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	6.0	—	Vdc
Base Cutoff Current (V_{CE} = 30 Vdc, V_{EB} = 3.0 Vdc)		I_{BL}	—	50	nAdc
Collector Cutoff Current (V_{CE} = 30 Vdc, V_{EB} = 3.0 Vdc)		I_{CEX}	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain(1)		h_{FE}			—
(I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc)	MMBT3903		20	—	
	MMBT3904		40	—	
(I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc)	MMBT3903		35	—	
	MMBT3904		70	—	
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	MMBT3903		50	150	
	MMBT3904		100	300	
(I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	MMBT3903		30	—	
	MMBT3904		60	—	
(I_C = 100 mAdc, V_{CE} = 1.0 Vdc)	MMBT3903		15	—	
	MMBT3904		30	—	
Collector-Emitter Saturation Voltage(1)		$V_{CE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)			—	0.2	
(I_C = 50 mAdc, I_B = 5.0 mAdc)			—	0.3	
Base-Emitter Saturation Voltage(1)		$V_{BE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)			0.65	0.85	
(I_C = 50 mAdc, I_B = 5.0 mAdc)			—	0.95	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)		f_T			MHz
	MMBT3903		250	—	
	MMBT3904		300	—	

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	4.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	8.0	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MMBT3903 MMBT3904	h_{ie}	1.0 1.0	8.0 10	k ohms
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MMBT3903 MMBT3904	h_{re}	0.1 0.5	5.0 8.0	X 10^{-4}
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MMBT3903 MMBT3904	h_{fe}	50 100	200 400	—
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{oe}	1.0	40	μmhos
Noise Figure (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 k ohms, f = 10 Hz to 15.7 kHz)	MMBT3903 MMBT3904	NF	— —	6.0 5.0	dB

SWITCHING CHARACTERISTICS

Characteristic	Conditions		Symbol	Min	Max	Unit
Delay Time	(V_{CC} = 3.0 Vdc, V_{BE} = 0.5 Vdc, I_C = 10 mAdc, I_{B1} = 1.0 mAdc)		t_d	—	35	ns
Rise Time			t_r	—	35	ns
Storage Time	(V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)	MMBT3903 MMBT3904	t_s	— —	175 200	ns
Fall Time			t_f	—	50	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

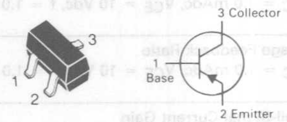
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT3906 = 2A

MMBT3906

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

Refer to 2N3905 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	Vdc
Base Cutoff Current (V_{CE} = 30 Vdc, V_{BE} = 3.0 Vdc)	I_{BL}	—	50	nAdc
Collector Cutoff Current (V_{CE} = 30 Vdc, V_{BE} = 3.0 Vdc)	I_{CEX}	—	50	nAdc
ON CHARACTERISTICS(1)				
DC Current Gain	h_{FE}			—
(I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc)		60	—	
(I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc)		80	—	
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)		100	300	
(I_C = 50 mAdc, V_{CE} = 1.0 Vdc)		60	—	
(I_C = 100 mAdc, V_{CE} = 1.0 Vdc)		30	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)		—	0.25	
(I_C = 50 mAdc, I_B = 5.0 mAdc)		—	0.4	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)		0.65	0.85	
(I_C = 50 mAdc, I_B = 5.0 mAdc)		—	0.95	
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	250	—	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	4.5	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)	C_{ibo}	—	10.0	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{ie}	2.0	12	k ohms
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{re}	0.1	10	$X 10^{-4}$
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{fe}	100	400	—

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{oe}	3.0	60	μmhos
Noise Figure (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 k ohm, f = 10 10 Hz to 15.7 kHz)	NF	—	4.0	dB

SWITCHING CHARACTERISTICS

Characteristic	Conditions	Symbol	Min	Max	Unit
Delay Time	(V_{CC} = 3.0 Vdc, V_{BE} = 0.5 Vdc I_C = 10 mAdc, I_{B1} = 1.0 mAdc)	t_d	—	35	ns
Rise Time		t_r	—	35	ns
Storage Time	(V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)	t_s	—	225	ns
Fall Time		t_f	—	75	ns

(1) Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	V
Collector-Base Voltage	V_{CBO}	40	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current — Continuous	I_C	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

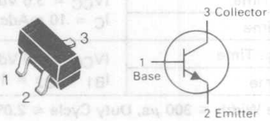
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT4123 = 5B

MMBT4123

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N4123 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

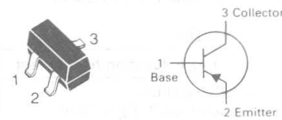
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_E = 0$)	$V_{(BR)CEO}$	25	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	30	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$)	I_{CBO}	—	50	nAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	50	nAdc
ON CHARACTERISTICS				
DC Current Gain(1) ($I_C = 2.0$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	 50 25	 150 —	—
Collector-Emitter Saturation Voltage(1) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)	$V_{CE(sat)}$	—	0.3	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)	$V_{BE(sat)}$	—	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)	f_T	250	—	MHz
Output Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	4.0	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz)	C_{ibo}	—	8.0	pF
Collector-Base Capacitance ($I_E = 0$, $V_{CB} = 5.0$ V, f = 100 kHz)	C_{cb}	—	4.0	pF
Small-Signal Current Gain ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	50	200	—
Current Gain — High Frequency ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)	$\|h_{fe}\|$	2.5	—	—
Noise Figure ($I_C = 100\ \mu$Adc, $V_{CE} = 5.0$ Vdc, $R_S = 1.0$ kohm, Noise Bandwidth = 10 Hz to 15.7 kHz)	NF	—	6.0	dB

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

MMBT4125

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

Refer to 2N4125 for graphs.

3

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT4125 = 2D

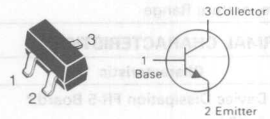
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_E = 0)	$V_{(BR)CEO}$	30	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	30	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0)	I_{CBO}	—	50	nAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)	I_{EBO}	—	50	nAdc
ON CHARACTERISTICS				
DC Current Gain(1) (I_C = 2.0 mAdc, V_{CE} = 1.0 Vdc) (I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	h_{FE}	50 25	150 —	—
Collector-Emitter Saturation Voltage(1) (I_C = 50 mAdc, I_B = 5.0 mAdc)	$V_{CE(sat)}$	—	0.4	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 50 mAdc, I_B = 5.0 mAdc)	$V_{BE(sat)}$	—	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	200	—	MHz
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)	C_{ibo}	—	10	pF
Collector-Base Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz)	C_{cb}	—	4.5	pF
Small-Signal Current Gain (I_C = 2.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{fe}	50	200	—
Current Gain — High Frequency (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	$\|h_{fe}\|$	2.0	—	—
Noise Figure (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 kohm, Noise Bandwidth = 10 Hz to 15.7 kHz)	NF	—	5.0	dB

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

MMBT4401

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



SWITCHING TRANSISTOR

NPN SILICON

Refer to 2N4401 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT4401 = 2X

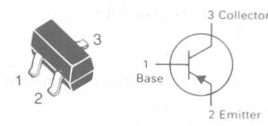
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1)	(I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage	(I_C = 0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage	(I_E = 0.1 mAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	—	Vdc
Base Cutoff Current	(V_{CE} = 35 Vdc, V_{EB} = 0.4 Vdc)	I_{BEV}	—	0.1	μAdc
Collector Cutoff Current	(V_{CE} = 35 Vdc, V_{EB} = 0.4 Vdc)	I_{CEX}	—	0.1	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain	(I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc)	h_{FE}	20	—	—
	(I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc)		40	—	
	(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)		80	—	
	(I_C = 150 mAdc, V_{CE} = 1.0 Vdc)		100	300	
	(I_C = 500 mAdc, V_{CE} = 2.0 Vdc)		40	—	
Collector-Emitter Saturation Voltage	(I_C = 150 mAdc, I_B = 15 mAdc)	$V_{CE(sat)}$	—	0.4	Vdc
	(I_C = 500 mAdc, I_B = 50 mAdc)		—	0.75	
Base-Emitter Saturation Voltage	(I_C = 150 mAdc, I_B = 15 mAdc)	$V_{BE(sat)}$	0.75	0.95	Vdc
	(I_C = 500 mAdc, I_B = 50 mAdc)		—	1.2	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	250	—	MHz
Collector-Base Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz)		C_{cb}	—	6.5	pF
Emitter-Base Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{eb}	—	30	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{ie}	1.0	15	k ohms
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{re}	0.1	8.0	$\times 10^{-4}$
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{fe}	40	500	—
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{oe}	1.0	30	μmhos
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 30 Vdc, V_{EB} = 2.0 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_d	—	15	ns
Rise Time		t_r	—	20	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_s	—	225	ns
Fall Time		t_f	—	30	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MMBT4403

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



SWITCHING TRANSISTOR

PNP SILICON

Refer to 2N4402 for graphs.

3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT4403 = 2T

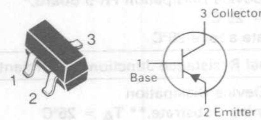
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1)	(I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage	(I_C = 0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage	(I_E = 0.1 mAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	Vdc
Base Cutoff Current	(V_{CE} = 35 Vdc, V_{BE} = 0.4 Vdc)	I_{BEV}	—	0.1	μAdc
Collector Cutoff Current	(V_{CE} = 35 Vdc, V_{BE} = 0.4 Vdc)	I_{CEX}	—	0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain	(I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc) (I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc) (I_C = 150 mAdc, V_{CE} = 2.0 Vdc)(1) (I_C = 500 mAdc, V_{CE} = 2.0 Vdc)(1)	h_{FE}	30 60 100 100 20	— — — 300 —	—
Collector-Emitter Saturation Voltage(1)	(I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)	$V_{CE(sat)}$	— —	0.4 0.75	Vdc
Base-Emitter Saturation Voltage(1)	(I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)	$V_{BE(sat)}$	0.75 —	0.95 1.3	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product	(I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	200	—	MHz
Collector-Base Capacitance	(V_{CB} = 10 Vdc, I_E = 0, f = 140 kHz)	C_{cb}	—	8.5	pF
Emitter-Base Capacitance	(V_{BE} = 0.5 Vdc, I_C = 0, f = 140 kHz)	C_{eb}	—	30	pF
Input Impedance	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{ie}	1.5k	15k	ohms
Voltage Feedback Ratio	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{re}	0.1	8.0	X 10^{-4}
Small-Signal Current Gain	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{fe}	60	500	—
Output Admittance	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{oe}	1.0	100	μmhos
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 30 Vdc, V_{BE} = 2.0 Vdc,	t_d	—	15	ns
Rise Time	I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_r	—	20	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc,	t_s	—	225	ns
Fall Time	I_{B1} = I_{B2} = 15 mAdc)	t_f	—	30	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MMBT5086
MMBT5087

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



LOW NOISE TRANSISTOR

PNP SILICON

Refer to 2N5086 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector-Base Voltage	V_{CBO}	50	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	50	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT5086 = 2P; MMBT5087 = 2Q

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)		$V_{(BR)CEO}$	50	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)		$V_{(BR)CBO}$	50	—	Vdc
Collector Cutoff Current		I_{CBO}			nAdc
(V_{CB} = 10 Vdc, I_E = 0)			—	10	
(V_{CB} = 35 Vdc, I_E = 0)			—	50	
ON CHARACTERISTICS					
DC Current Gain		h_{FE}			—
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	MMBT5086		150	500	
	MMBT5087		250	800	
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	MMBT5086		150		
	MMBT5087		250	—	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	MMBT5086		150	—	
	MMBT5087		250	—	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{CE(sat)}$	—	0.3	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{BE(sat)}$	—	0.85	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 500 μAdc, V_{CE} = 5.0 Vdc, f = 20 MHz)		f_T	40	—	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	4.0	pF
Small-Signal Current Gain		h_{fe}			—
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	MMBT5086		150	600	
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	MMBT5087		250	900	
Noise Figure		NF			dB
(I_C = 20 mAdc, V_{CE} = 5.0 Vdc, R_S = 10 kΩ, f = 10 Hz to 15.7 kHz)	MMBT5086		—	3.0	
	MMBT5087		—	2.0	
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 3.0 kΩ, f = 1.0 kHz)	MMBT5086		—	3.0	
	MMBT5087		—	2.0	

MAXIMUM RATINGS

Rating	Symbol	Value MMBT5088	Value MMBT5089	Unit
Collector-Emitter Voltage	V_{CEO}	30	25	Vdc
Collector-Base Voltage	V_{CBO}	35	30	Vdc
Emitter-Base Voltage	V_{EBO}	4.5		Vdc
Collector Current — Continuous	I_C	50		mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

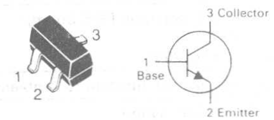
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT5088 = 1Q; MMBT5089 = 1R

MMBT5088
MMBT5089

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



LOW NOISE TRANSISTOR

NPN SILICON

Refer to MPSA18 for graphs.

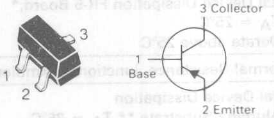
3

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	MMBT5088 MMBT5089	$V_{(BR)CEO}$	30 25	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	MMBT5088 MMBT5089	$V_{(BR)CBO}$	35 30	— —	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0) (V_{CB} = 15 Vdc, I_E = 0)	MMBT5088 MMBT5089	I_{CBO}	— —	50 50	nAdc
Emitter Cutoff Current ($V_{EB(off)}$ = 3.0 Vdc, I_C = 0) ($V_{EB(off)}$ = 4.5 Vdc, I_C = 0)	MMBT5088 MMBT5089	I_{EBO}	— —	50 100	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	MMBT5088 MMBT5089	h_{FE}	300 400	900 1200	—
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	MMBT5088 MMBT5089		350 450	— —	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	MMBT5088 MMBT5089		300 400	— —	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{BE(sat)}$	—	0.8	Vdc
SMALL SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 500 μAdc, V_{CE} = 5.0 Vdc, f = 20 MHz)		f_T	50	—	MHz
Collector-Base Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz emitter guarded)		C_{cb}	—	4.0	pF
Emitter-Base Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz collector guarded)		C_{eb}	—	10	pF
Small Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	MMBT5088 MMBT5089	h_{fe}	350 450	1400 1800	—
Noise Figure (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 kΩ, f = 10 Hz to 15.7 Hz)	MMBT5088 MMBT5089	NF	— —	3.0 2.0	dB

Collector-Base Voltage	V_{CBO}	160	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	500	mAdc

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

HIGH VOLTAGE TRANSISTOR

PNP SILICON

DEVICE MARKING

MMBT5401 = 2L

Refer to 2N5401 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	150	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	160	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 100$ Vdc, $I_E = 0$) ($V_{CB} = 100$ Vdc, $I_E = 0$, $T_A = 150°C$)	I_{CBO}	— —	50 50	nAdc μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 50$ mAdc, $V_{CE} = 5.0$ Vdc)	h_{FE}	50 60 50	— 240 —	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)	$V_{CE(sat)}$	— —	0.20 0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)	$V_{BE(sat)}$	— —	1.0 1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	100	300	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{obo}		6.0	pF
Small Signal Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	40	200	—
Noise Figure ($I_C = 200\ \mu$Adc, $V_{CE} = 5.0$ Vdc, $R_S = 10$ ohms, f = 10 Hz to 15.7 kHz)	NF	—	8.0	dB

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	140	Vdc
Collector-Base Voltage	V_{CBO}	160	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

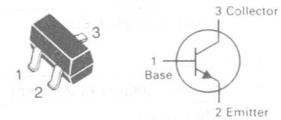
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT5550 = 1F; MMBT5551 = G1

MMBT5550
MMBT5551

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



HIGH VOLTAGE TRANSISTOR

NPN SILICON

Refer to 2N5550 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 1.0 mAdc, I_B = 0)	MMBT5550	$V_{(BR)CEO}$	140	—	Vdc
	MMBT5551		160	—	
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	MMBT5550	$V_{(BR)CBO}$	160	—	Vdc
	MMBT5551		180	—	
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current (V_{CB} = 100 Vdc, I_E = 0)	MMBT5550	I_{CBO}	—	100	nAdc
(V_{CB} = 120 Vdc, I_E = 0)	MMBT5551		—	50	
(V_{CB} = 100 Vdc, I_E = 0, T_A = 100°C)	MMBT5550		—	100	μAdc
(V_{CB} = 120 Vdc, I_E = 0, T_A = 100°C)	MMBT5551		—	50	
Emitter Cutoff Current (V_{EB} = 4.0 Vdc, I_C = 0)		I_{EBO}	—	50	nAdc
ON CHARACTERISTICS(2)					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	MMBT5550	h_{FE}	60	—	—
	MMBT5551		80	—	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	MMBT5550		60	250	
	MMBT5551		80	250	
(I_C = 50 mAdc, V_{CE} = 5.0 Vdc)	MMBT5550		20	—	
	MMBT5551		30	—	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	Both Types	$V_{CE(sat)}$	—	0.15	Vdc
(I_C = 50 mAdc, I_B = 5.0 mAdc)	MMBT5550		—	0.25	
	MMBT5551		—	0.20	
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	Both Types	$V_{BE(sat)}$	—	1.0	Vdc
(I_C = 50 mAdc, I_B = 5.0 mAdc)	MMBT5550		—	1.2	
	MMBT5551		—	1.0	

(2) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	12	Vdc
Collector Current — Continuous	I_C	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

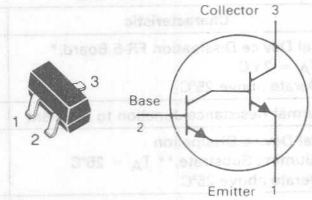
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT6427 = 1V

MMBT6427

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



DARLINGTON TRANSISTOR

NPN SILICON

Refer to 2N6426 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40		Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	12	—	Vdc
Collector Cutoff Current ($V_{CE} = 25$ Vdc, $I_B = 0$)	I_{CEO}	—	1.0	μAdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	50	nAdc
Emitter Cutoff Current ($V_{BE} = 10$ Vdc, $I_C = 0$)	I_{EBO}	—	50	nAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 500$ mAdc, $V_{CE} = 5.0$ Vdc)	h_{FE}	10,000 20,000 14,000	100,000 200,000 140,000	
Collector-Emitter Saturation Voltage ($I_C = 50$ mAdc, $I_B = 0.5$ mAdc) ($I_C = 500$ mAdc, $I_B = 0.5$ mAdc)	$V_{CE(sat)}$	—	1.2 1.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 500$ mAdc, $I_B = 0.5$ mAdc)	$V_{BE(sat)}$	—	2.0	Vdc
Base-Emitter On Voltage ($I_C = 50$ mAdc, $V_{CE} = 5.0$ Vdc)	$V_{BE(on)}$	—	1.75	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{obo}	—	7.0	pF
Input Capacitance ($V_{BE} = 0.5$, $I_C = 0$, f = 1.0 MHz)	C_{ibo}	—	15	pF
Current Gain — High Frequency ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc, f = 100 MHz)	$\lvert h_{fe} \rvert$	1.3	—	Vdc
Noise Figure ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, $R_S = 100$ kΩ, f = 1.0 kHz to 15.7 kHz)	NF	—	10	dB

MAXIMUM RATINGS

Rating	Symbol	Value MMBT6428	Value MMBT6429	Unit
Collector-Emitter Voltage	V_{CEO}	50	45	Vdc
Collector-Base Voltage	V_{CBO}	60	55	Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	200		mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

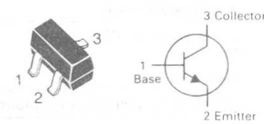
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT6428 = 1K; MMBT6429 = 1L

MMBT6428
MMBT6429

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MPSA18 for graphs.

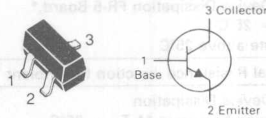
3

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$) ($I_C = 1.0$ mAdc, $I_B = 0$)	 MMBT6428 MMBT6429	$V_{(BR)CEO}$	 50 45	 — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.1$ mAdc, $I_E = 0$) ($I_C = 0.1$ mAdc, $I_E = 0$)	 MMBT6428 MMBT6429	$V_{(BR)CBO}$	 60 55	 — —	Vdc
Collector Cutoff Current ($V_{CE} = 30$ Vdc)		I_{CEO}	—	0.1	μAdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)		I_{CBO}	—	0.01	μAdc
Emitter Cutoff Current ($V_{EB} = 5.0$ Vdc, $I_C = 0$)		I_{EBO}	—	0.01	μAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 0.01$ mAdc, $V_{CE} = 5.0$ Vdc)	 MMBT6428 MMBT6429	h_{FE}	 250 500	 — —	—
($I_C = 0.1$ mAdc, $V_{CE} = 5.0$ Vdc)	MMBT6428 MMBT6429		250 500	650 1250	
($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc)	MMBT6428 MMBT6429		250 500	— —	
($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc)	MMBT6428 MMBT6429		250 500	— —	
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 0.5$ mAdc) ($I_C = 100$ mAdc, $I_B = 5.0$ mAdc)		$V_{CE(sat)}$	 — —	 0.2 0.6	Vdc
Base-Emitter On Voltage ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc)		$V_{BE(on)}$	0.56	0.66	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 100 MHz)		f_T	100	700	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{obo}	—	3.0	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)		C_{ibo}	—	8.0	pF

MMBT6517

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



HIGH VOLTAGE TRANSISTOR

NPN SILICON

Refer to 2N6517 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	350	Vdc
Collector-Base Voltage	V_{CBO}	350	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Base Current	I_B	250	mA
Collector Current — Continuous	I_C	500	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

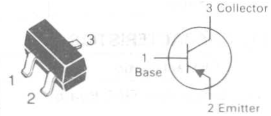
MMBT6517 = 1Z

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 1.0 mA)	$V_{(BR)CEO}$	350	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μA)	$V_{(BR)CBO}$	350	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μA)	$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current (V_{CB} = 250 V)	I_{CBO}	—	50	nA
Emitter Cutoff Current (V_{EB} = 5.0 V)	I_{EBO}	—	50	nA
ON CHARACTERISTICS				
DC Current Gain (I_C = 1.0 mA, V_{CE} = 10 V) (I_C = 10 mA, V_{CE} = 10 V) (I_C = 30 mA, V_{CE} = 10 V) (I_C = 50 mA, V_{CE} = 10 V) (I_C = 100 mA, V_{CE} = 10 V)	h_{FE}	 20 30 30 20 15	 — — 200 200 —	—
Collector-Emitter Saturation Voltage (I_C = 10 mA, I_B = 1.0 mA) (I_C = 20 mA, I_B = 2.0 mA) (I_C = 30 mA, I_B = 3.0 mA) (I_C = 50 mA, I_B = 5.0 mA)	$V_{CE(sat)}$	 — — — —	 0.30 0.35 0.50 1.0	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mA, I_B = 1.0 mA) (I_C = 20 mA, I_B = 2.0 mA) (I_C = 30 mA, I_B = 3.0 mA)	$V_{BE(sat)}$	 — — —	 0.75 0.85 0.90	Vdc
Base-Emitter On Voltage (I_C = 100 mA, V_{CE} = 10 V)	$V_{BE(on)}$	—	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 10 mA, V_{CE} = 20 V, f = 20 MHz)	f_T	40	200	MHz
Collector-Base Capacitance (V_{CB} = 20 V, f = 1.0 MHz)	C_{cb}	—	6.0	pF
Emitter-Base Capacitance (V_{EB} = 0.5 V, f = 1.0 MHz)	C_{eb}	—	80	pF

Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Base Current	I_B	250	mA
Collector Current — Continuous	I_C	500	mAdc

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



HIGH VOLTAGE TRANSISTOR

PNP SILICON

Refer to 2N6520 for graphs.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT6520 = 2Z

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 1.0 mA)	$V_{(BR)CEO}$	350	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μA)	$V_{(BR)CBO}$	350	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μA)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 250 V)	I_{CBO}	—	50	nA
Emitter Cutoff Current (V_{EB} = 4.0 V)	I_{EBO}	—	50	nA
ON CHARACTERISTICS				
DC Current Gain (I_C = 1.0 mA, V_{CE} = 10 V) (I_C = 10 mA, V_{CE} = 10 V) (I_C = 30 mA, V_{CE} = 10 V) (I_C = 50 mA, V_{CE} = 10 V) (I_C = 100 mA, V_{CE} = 10 V)	h_{FE}	 20 30 30 20 15	 — — 200 200 —	—
Collector-Emitter Saturation Voltage (I_C = 10 mA, I_B = 1.0 mA) (I_C = 20 mA, I_B = 2.0 mA) (I_C = 30 mA, I_B = 3.0 mA) (I_C = 50 mA, I_B = 5.0 mA)	$V_{CE(sat)}$	 — — — —	 0.30 0.35 0.50 1.0	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mA, I_B = 1.0 mA) (I_C = 20 mA, I_B = 2.0 mA) (I_C = 30 mA, I_B = 3.0 mA)	$V_{BE(sat)}$	 — — —	 0.75 0.85 0.90	Vdc
Base-Emitter On Voltage (I_C = 100 mA, V_{CE} = 10 V)	$V_{BE(on)}$			Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 10 mA, V_{CE} = 20 V, f = 20 MHz)	f_T	40	200	MHz
Collector-Base Capacitance (V_{CB} = 20 V, f = 1.0 MHz)	C_{cb}	—	6.0	pF
Emitter-Base Capacitance (V_{EB} = 0.5 V, f = 1.0 MHz)	C_{eb}	—	100	pF

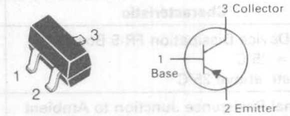
3

MAXIMUM RATINGS

Rating	Symbol	MMBT8598	MMBT8599	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	V
Collector-Base Voltage	V_{CBO}	60	80	V
Emitter-Base Voltage	V_{EBO}	5.0		V
Collector Current — Continuous	I_C	500		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	350 2.8		mW mW/°C
Operating and Storage Junction Temperature Range	T_{stg}	−55 to +150		°C

MMBT8598
MMBT8599

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

Refer to 2N4125 for graphs.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBT8598 = 2K; MMBT8599 = 2W

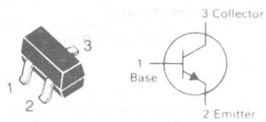
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_E = 0$)	MMBT8598 MMBT8599	$V_{(BR)CEO}$	60 80	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	MMBT8598 MMBT8599	$V_{(BR)CBO}$	60 80	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$)		I_{CBO}	—	50	nAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)		I_{EBO}	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) ($I_C = 100$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 5.0$ Vdc)		h_{FE}	50 25	150 —	
Collector-Emitter Saturation Voltage(1) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)		$V_{CE(sat)}$	—	0.4	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)		$V_{BE(sat)}$	—	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)		f_T	200		MHz
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz)		C_{ibo}	—	10	pF
Collector-Base Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 100 kHz)		C_{cb}	—	4.5	pF
Small-Signal Current Gain ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)		h_{fe}	50	200	—
Current Gain — High Frequency ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)		$\|h_{fe}\|$	2.0	—	—
Noise Figure ($I_C = 100\ \mu$Adc, $V_{CE} = 5.0$ Vdc, $R_S = 1.0$ kohm, Noise Bandwidth = 10 Hz to 15.7 kHz)		NF	—	5.0	dB

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

MMBTA05
MMBTA06

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



DRIVER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	MMBTA05	MMBTA06	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	Vdc
Collector-Base Voltage	V_{CBO}	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	4.0		Vdc
Collector Current — Continuous	I_C	500		mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBTA05 = 1H; MMBTA06 = 1G

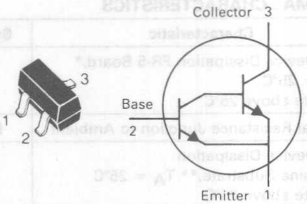
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)	 MMBTA05 MMBTA06	$V_{(BR)CEO}$	 60 80	 — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current (V_{CE} = 60 Vdc, I_B = 0)		I_{CEO}	—	0.1	μAdc
Collector Cutoff Current (V_{CB} = 60 Vdc, I_E = 0) (V_{CB} = 80 Vdc, I_E = 0)	 MMBTA05 MMBTA06	I_{CBO}	 — —	 0.1 0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 10 mAdc, V_{CE} = 1.0 Vdc) (I_C = 100 mAdc, V_{CE} = 1.0 Vdc)		h_{FE}	 50 50	 — —	—
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 10 mAdc)		$V_{CE(sat)}$	—	0.25	Vdc
Base-Emitter On Voltage (I_C = 100 mAdc, V_{CE} = 1.0 Vdc)		$V_{BE(on)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 10 mA, V_{CE} = 2.0 V, f = 100 MHz)		f_T	100	—	MHz

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

Emitter-Base Voltage	V_{EBO}	10	Vdc
Collector Current — Continuous	I_C	300	mAdc

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



DARLINGTON AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N6426 for graphs.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBTA13 = 1M; MMBTA14 = 1N

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 100 μAdc, I_B = 0)		$V_{(BR)CES}$	30		Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)		I_{CBO}	—	100	nAdc
Emitter Cutoff Current (V_{BE} = 10 Vdc, I_C = 0)		I_{EBO}	—	100	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	MMBTA13 MMBTA14	h_{FE}	5000 10,000	— —	—
(I_C = 100 mAdc, V_{CE} = 5.0 Vdc)	MMBTA13 MMBTA14		10,000 20,000	— —	
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 0.1 mAdc)		$V_{CE(sat)}$	—	1.5	Vdc
Base-Emitter On Voltage (I_C = 100 mAdc, V_{CE} = 5.0 Vdc)		V_{BE}	—	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)		f_T	125	—	MHz

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) $f_T = |h_{fe}| \cdot f_{test}$.

Collector Current — Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

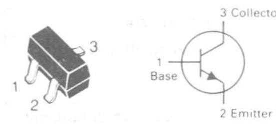
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBTA20 = 1C

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



GENERAL PURPOSE AMPLIFIER

NPN SILICON

Refer to MPS3904 for graphs.

3

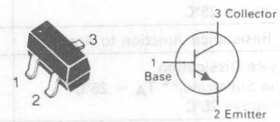
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	100	nAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	40	400	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	0.25	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	125	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	4.0	pF

3

MMBTA42
MMBTA43

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



HIGH VOLTAGE TRANSISTOR

NPN SILICON

Refer to MPSA42 for graphs.

MAXIMUM RATINGS

Rating	Symbol	MMBTA42	MMBTA43	Unit
Collector-Emitter Voltage	V_{CEO}	300	200	Vdc
Collector-Base Voltage	V_{CBO}	300	200	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	6.0	Vdc
Collector Current — Continuous	I_C	500		mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBTA42 = 1D; MMBTA43 = 1E

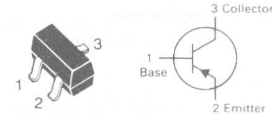
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	MMBTA42 MMBTA43	$V_{(BR)CEO}$	300 200	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	MMBTA42 MMBTA43	$V_{(BR)CBO}$	300 200	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 200$ Vdc, $I_E = 0$) ($V_{CB} = 160$ Vdc, $I_E = 0$)	MMBTA42 MMBTA43	I_{CBO}	— —	0.1 0.1	μAdc
Emitter Cutoff Current ($V_{BE} = 6.0$ Vdc, $I_C = 0$) ($V_{BE} = 4.0$ Vdc, $I_C = 0$)	MMBTA42 MMBTA43	I_{EBO}	— —	0.1 0.1	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc)	Both Types	h_{FE}	25	—	—
($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc)	Both Types		40	—	
($I_C = 30$ mAdc, $V_{CE} = 10$ Vdc)	MMBTA42 MMBTA43		40 40	—	
Collector-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)	MMBTA42 MMBTA43	$V_{CE(sat)}$	— —	0.5 0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)		$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)		f_T	50	—	MHz
Collector-Base Capacitance ($V_{CB} = 20$ Vdc, $I_E = 0$, f = 1.0 MHz)	MMBTA42 MMBTA43	C_{cb}	— —	3.0 4.0	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MMBTA55
MMBTA56

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



DRIVER TRANSISTOR

PNP SILICON

3

MAXIMUM RATINGS

Rating	Symbol	MMBTA55	MMBTA56	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	Vdc
Collector-Base Voltage	V_{CBO}	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	4.0		Vdc
Collector Current — Continuous	I_C	500		mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBTA55 = 2H; MMBTA56 = 2G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)	MMBTA55 MMBTA56	$V_{(BR)CEO}$	60 80	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current (V_{CE} = 60 Vdc, I_B = 0)		I_{CEO}	—	0.1	μAdc
Collector Cutoff Current (V_{CB} = 60 Vdc, I_E = 0) (V_{CB} = 80 Vdc, I_E = 0)	 MMBTA55 MMBTA56	I_{CBO}	 — —	 0.1 0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 10 mAdc, V_{CE} = 1.0 Vdc) (I_C = 100 mAdc, V_{CE} = 1.0 Vdc)		h_{FE}	 50 50	 — —	—
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 10 mAdc)		$V_{CE(sat)}$	—	0.25	Vdc
Base-Emitter On Voltage (I_C = 100 mAdc, V_{CE} = 1.0 Vdc)		$V_{BE(on)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 100 mAdc, V_{CE} = 1.0 Vdc, f = 100 MHz)		f_T	50	—	MHz

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CES}	30	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	10	Vdc
Collector Current — Continuous	I_C	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

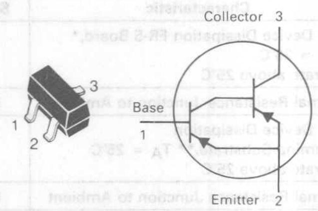
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBTA63 = 2V; MMBTA64 = 2U

MMBTA63
MMBTA64

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



DARLINGTON TRANSISTOR

PNP SILICON

Refer to MPSA75 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 100 μAdc)		$V_{(BR)CES}$	30	—	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc)		I_{CBO}	—	100	nAdc
Emitter Cutoff Current (V_{BE} = 10 Vdc)		I_{EBO}	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain(1)		h_{FE}			
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	MMBTA63		5,000	—	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	MMBTA64		10,000	—	
(I_C = 100 mAdc, V_{CE} = 5.0 Vdc)	MMBTA63		10,000	—	
(I_C = 100 mAdc, V_{CE} = 5.0 Vdc)	MMBTA64		20,000	—	
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 0.1 mAdc)		$V_{CE(sat)}$	—	1.5	Vdc
Base-Emitter On Voltage (I_C = 100 mAdc, V_{CE} = 5.0 Vdc)		$V_{BE(on)}$	—	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)		f_T	125	—	MHz

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

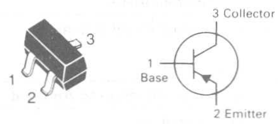
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBTA70 = 2C

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



3

GENERAL PURPOSE TRANSISTOR

PNP SILICON

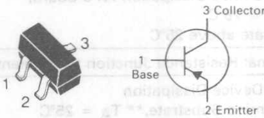
Refer to 2N5086 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	—	100	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 5.0 mAdc, V_{CE} = 10 Vdc)	h_{FE}	40	400	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{CE(sat)}$	—	0.25	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 5.0 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	125	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	4.0	pF

MMBTA92
MMBTA93

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



HIGH VOLTAGE TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	MMBTA92	MMBTA93	Unit
Collector-Emitter Voltage	V_{CEO}	300	200	Vdc
Collector-Base Voltage	V_{CBO}	300	200	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	5.0	Vdc
Collector Current — Continuous	I_C	500		mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBTA92 = 2D; MMBTA93 = 2E

Refer to MPSA92 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	MMBTA92	$V_{(BR)CEO}$	300	—	Vdc
	MMBTA93		200	—	
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	MMBTA92	$V_{(BR)CBO}$	300		Vdc
	MMBTA93		200		
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	5.0		Vdc
Collector Cutoff Current ($V_{CB} = 200$ Vdc, $I_E = 0$)	MMBTA92	I_{CBO}	—	0.25	μAdc
($V_{CB} = 160$ Vdc, $I_E = 0$)	MMBTA93			0.25	
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)		I_{EBO}		0.1	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc)	Both Types	h_{FE}	25	—	
($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc)	Both Types		40	—	
($I_C = 30$ mAdc, $V_{CE} = 10$ Vdc)	MMBTA92		25	—	
	MMBTA93		25	—	
Collector-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)	MMBTA92	$V_{CE(sat)}$	—	0.5	Vdc
	MMBTA93		—	0.5	
Base-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)		$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)		f_T	50	—	MHz
Collector-Base Capacitance ($V_{CB} = 20$ Vdc, $I_E = 0$, f = 1.0 MHz)	MMBTA92	C_{cb}	—	6.0	pF
	MMBTA93		—	8.0	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

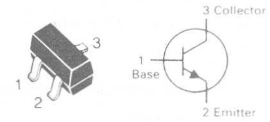
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBTH10 = 3E

MMBTH10

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



VHF/UHF TRANSISTOR

NPN SILICON

3

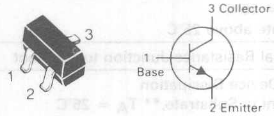
Refer to MPSH10 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	25	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	30	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 25$ Vdc, $I_E = 0$)	I_{CBO}	—	100	nAdc
Emitter Cutoff Current ($V_{BE} = 2.0$ Vdc, $I_C = 0$)	I_{EBO}	—	100	nAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	60	—	—
Collector-Emitter Saturation Voltage ($I_C = 4.0$ mAdc, $I_B = 0.4$ mAdc)	$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter On Voltage ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc)	V_{BE}	—	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	650	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{cb}	—	0.7	pF
Common-Base Feedback Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{rb}	—	0.65	pF
Collector Base Time Constant ($I_C = 4.0$ mAdc, $V_{CB} = 10$ Vdc, f = 31.8 MHz)	$rb'C_c$	—	9.0	ps

MMBTH24

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



VHF MIXER TRANSISTOR

NPN SILICON

3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBTH24 = 3A

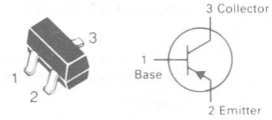
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 15 Vdc, I_E = 0)	I_{CBO}	—	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 8.0 mAdc, V_{CE} = 10 Vdc)	h_{FE}	30	—	—	—
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(1) (I_C = 8.0 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	400	620	—	MHz
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	—	0.25	0.36	pF
Conversion Gain	—				dB
(213 MHz to 45 MHz) (I_C = 8.0 mAdc, V_{CC} = 20 Vdc, Oscillator Injection = 150 mVrms)	C_G	19	24	—	
(60 MHz to 45 MHz) (I_C = 8.0 mAdc, V_{CC} = 20 Vdc, Oscillator Injection = 150 mVrms)		24	29	—	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

Collector-Emitter Voltage	V_{CEO}	20	Vdc
Collector-Base Voltage	V_{CBO}	20	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc

CASE 318-02/03, STYLE 6
SOT-23 (TO-236AA/AB)



UHF/VHF TRANSISTOR

PNP SILICON

3

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBTH81 = 3D

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	20	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	20	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 10$ Vdc, $I_E = 0$)	I_{CBO}	—	—	100	nAdc
Emitter Cutoff Current ($V_{BE} = 2.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	60	—	—	—
Collector-Emitter Saturation Voltage ($I_C = 5.0$ mAdc, $I_B = 0.5$ mAdc)	$V_{CE(sat)}$	—	—	0.5	Vdc
Base-Emitter On Voltage ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc)	$V_{BE(on)}$	—	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	600	—	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{cb}	—	—	0.85	pF
Collector-Emitter Capacitance ($I_B = 0$, $V_{CB} = 10$ Vdc, f = 1.0 MHz)	C_{ce}	—	—	0.65	pF

MMBV105G

CASE 318-02/03, STYLE 8
SOT-23 (TO-236AA/AB)

VOLTAGE VARIABLE CAPACITANCE DIODE

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	30	Vdc
Forward Current	I_F	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBV105G = 4E

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Reverse Breakdown Voltage (I_R = 10 μAdc)	$V_{(BR)}$	30	—	—	Vdc
Reverse Voltage Leakage Current (V_R = 28 Vdc)	I_R	—	—	50	nAdc
Series Inductance (f = 250 MHz)	L_S	—	3.0	—	nH
Diode Capacitance Temperature Coefficient (V_R = 3.0 Vdc, f = 1.0 MHz)	TC_C	—	280	—	ppm/°C
Diode Capacitance (V_R = 25 Vdc)	C_T	1.8	—	2.8	pF
Capacitance Ratio (V_{R1} = 3.0 Vdc, V_{R2} = 25 Vdc, f = 1.0 MHz)	C3/C25	4.0	—	6.0	—

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	30	Vdc
Forward Current	I_F	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

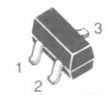
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBV109 = 4A

MMBV109

CASE 318-02/03, STYLE 8
SOT-23 (TO-236AA/AB)



VOLTAGE VARIABLE CAPACITANCE DIODE

3

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Reverse Breakdown Voltage (I_R = 10 μAdc)	$V_{(BR)}$	30	—	—	Vdc
Reverse Voltage Leakage Current (V_R = 28 Vdc)	I_R	—	—	0.1	μAdc
Series Inductance (f = 250 MHz)	L_S	—	3.0	—	nH
Case Capacitance (f = 1.0 MHz)	C_C	—	0.1	—	pF
Diode Capacitance Temperature Coefficient (V_R = 3.0 Vdc, f = 1.0 MHz)	TC_C	—	280	—	ppm/°C
Figure of Merit (V_R = 3.0 Vdc, f = 50 MHz)	Q	200	—	—	—
Diode Capacitance (V_R = 3.0 Vdc, f = 1.0 MHz)	C_T	26	—	32	pF

MMBV409
MMBV409L
MV409

CASE 182-02, STYLE 1
(TO-226AC)

CASE 318-02, STYLE 8
SOT-23 (TO-236AA)

VOLTAGE VARIABLE CAPACITANCE DIODE

MAXIMUM RATINGS

Rating	Symbol	MV409	MMBV409,L	Unit
		Value		
Reverse Voltage	V_R	20		Volts
Forward Current	I_F	200		mA
Forward Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	280 2.8	225* 1.8	mW mW/°C
Junction Temperature	T_J	+125		°C
Storage Temperature Range	T_{stg}	−65 to +150		°C

*FR5 Board 1.0 x 0.75 x 0.62 in.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic — All Types	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I_R = 10 μAdc)	$V_{(BR)R}$	20	—	—	Vdc
Reverse Voltage Leakage Current (V_R = 15 Vdc)	I_R	—	—	0.1	μAdc
Diode Capacitance Temperature Coefficient (V_R = 3 Vdc, f = 1 MHz)	TC_C	—	300	—	ppm/°C

Device	C_t, Diode Capacitance V_R = 3 Vdc, f = 1 MHz pF			Q, Figure of Merit V_R = 3 Vdc f = 50 MHz (Note 1)	C_R, Capacitance Ratio C_3/C_8 f = 1 MHz (Note 2)	
	Min	Nom	Max	Min	Min	Max
MMBV409,L/MV409	26	29	32	200	1.5	1.9

NOTES ON TESTING AND SPECIFICATIONS

(1) Q is calculated by taking the G and C readings of an admittance bridge, such as Boonton Electronics Model 33AS8, at the specified frequency and substituting in the following equation:

$$Q = \frac{2\pi fC}{G}$$

(2) C_R is the ratio of C_t measured at 3 Vdc divided by C_t measured at 8 Vdc.

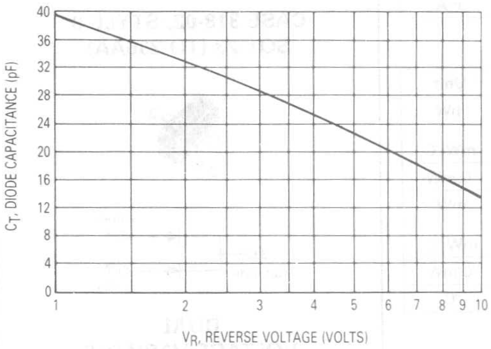


Figure 1. Diode Capacitance

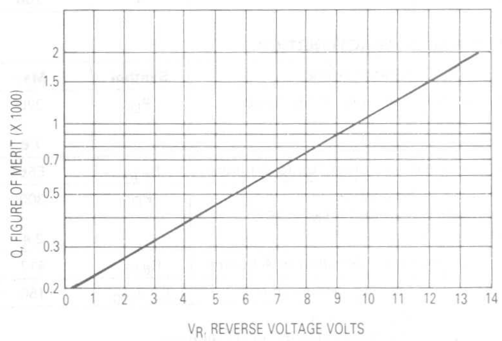


Figure 2. Figure of Merit

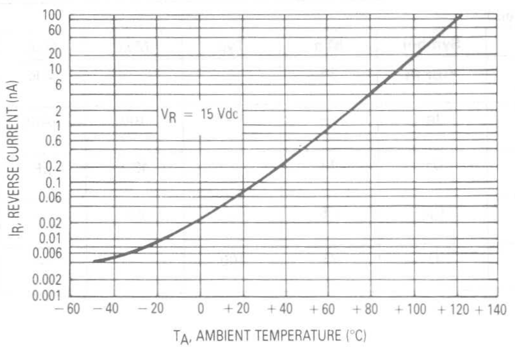


Figure 3. Leakage Current

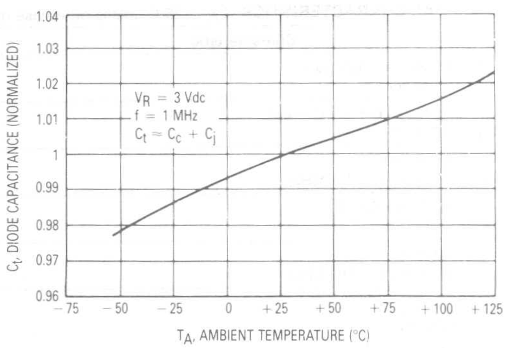


Figure 4. Diode Capacitance

MAXIMUM RATINGS (Each Diode)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	14	Volts
Forward Current	I_F	200	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

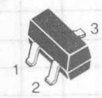
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

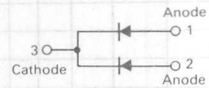
DEVICE MARKING

MMBV432L = 4B

MMBV432L

CASE 318-02, STYLE 9
SOT-23 (TO-236AA)





DUAL VOLTAGE-VARIABLE CAPACITANCE DIODE

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I_R = 10 μAdc)	$V_{(BR)R}$	14	—	—	Vdc
Reverse Voltage Leakage Current (V_R = 9.0 Vdc)	I_R	—	—	100	nAdc
Diode Capacitance (V_R = 2.0 Vdc, f = 1.0 MHz)	C_T	43	—	48.1	pF
Capacitance Ratio C2/C8 (f = 1.0 MHz)	C_R	1.5	—	2.0	—
Figure of Merit* (V_R = 2.0 Vdc, f = 100 MHz)	Q	75	100	—	—

$$* \; Q = \frac{1}{2 \pi f C_T R_S}$$

TYPICAL CHARACTERISTICS (Each Diode)

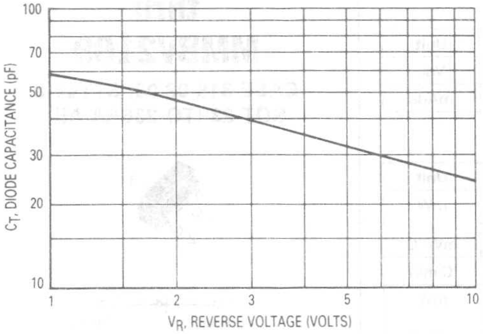


Figure 1. Diode Capacitance (Each Diode)

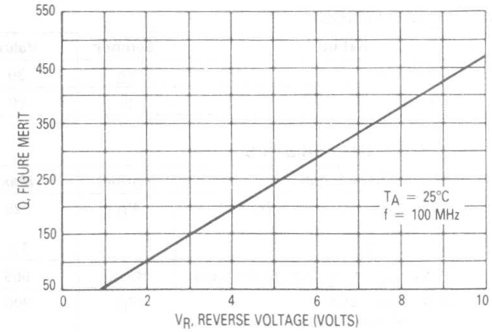


Figure 2. Figure of Merit versus Voltage

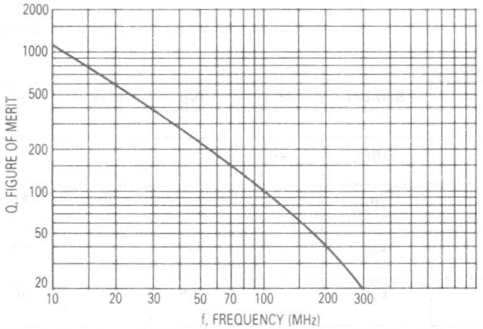


Figure 3. Figure of Merit versus Frequency

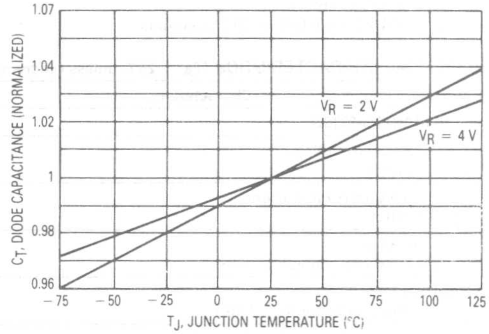


Figure 4. Diode Capacitance versus Temperature

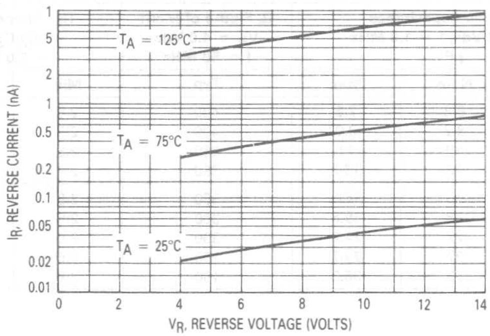


Figure 5. Reverse Current versus Reverse Voltage

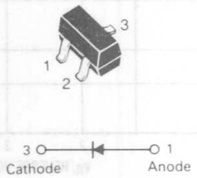
3

3

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	30	Vdc
Forward Current	I_F	20	mAdc

MMBV2109

CASE 318-02/03, STYLE 8
SOT-23 (TO-236AA/AB)



TUNING DIODE

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Reverse Breakdown Voltage (I_R = 10 μAdc)	$V_{(BR)}$	30	—	—	Vdc
Reverse Voltage Leakage Current (V_R = 25 Vdc)	I_R	—	—	20	nAdc
Series Inductance (f = 250 MHz, Lead Length ≈ 1/16")	L_S	—	3.0	—	nH
Case Capacitance (f = 1.0 MHz, Lead Length ≈ 1/16")	C_C	—	0.15	—	pF
Diode Capacitance Temperature Coefficient (V_R = 4.0 Vdc, f = 1.0 MHz)	TC_C	—	280	400	ppm/°C

Device	C_T, Diode Capacitance V_R = 4.0 Vdc, f = 1.0 MHz pF			Q, Figure of Merit V_R = 4.0 Vdc f = 50 MHz	TR, Tuning Ratio C_2/C_{30} f = 1.0 MHz		Marking
	Min	Nom	Max	Typ	Min	Max	Top
MMBV-2101	6.1	6.8	7.5	400	2.5	3.2	4G
MMBV-2102	7.3	8.2	9.0	400	2.5	3.2	4S
MMBV-2103	9.0	10	11	350	2.5	3.2	4H
MMBV2104	10.8	12	13.2	350	2.5	3.2	4T
MMBV-2105	13.5	15	16.5	350	2.5	3.2	4U
MMBV-2106	16.2	18	19.8	300	2.5	3.2	4V
MMBV-2107	19.8	22	24.2	300	2.5	3.2	4W
MMBV-2108	24.3	27	29.7	250	2.5	3.2	4X
MMBV-2109	29.7	33	36.3	150	2.5	3.2	4J

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	30	Vdc
Forward Current	I_F	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

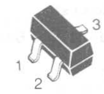
*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBV3102 = 4C

MMBV3102

CASE 318-02/03, STYLE 8
SOT-23 (TO-236AA/AB)



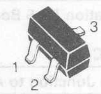
VOLTAGE VARIABLE CAPACITANCE DIODE

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Reverse Breakdown Voltage (I_R = 10 μAdc)	$V_{(BR)}$	30	—	—	Vdc
Reverse Voltage Leakage Current (V_R = 25 Vdc)	I_R	—	—	0.1	μAdc
Series Inductance (f = 250 MHz)	L_S	—	3.0	—	nH
Case Capacitance (f = 1.0 MHz)	C_C	—	0.1	—	pF
Diode Capacitance Temperature Coefficient (V_R = 3.0 Vdc, f = 1.0 MHz)	T_{CC}	—	280	—	ppm/°C
Figure of Merit (V_R = 3.0 Vdc, f = 50 MHz)	Q	200	—	—	—
Diode Capacitance (V_R = 3.0 Vdc, f = 1.0 MHz)	C_T	20	—	25	pF

MMBV3401

CASE 318-02/03, STYLE 8
SOT-23 (TO-236AA/AB)



SILICON PIN SWITCHING DIODE

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	35	Vdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBV3401 = 4D

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Reverse Breakdown Voltage (I_R = 10 μAdc)	$V_{(BR)}$	35	—	—	Vdc
Reverse Voltage Leakage Current (V_R = 25 Vdc)	I_R	—	—	0.1	μAdc
Series Inductance (f = 250 MHz)	L_S	—	3.0	—	nH
Series Resistance (I_F = 10 mAdc)	R_S	—	—	0.7	Ohms
Case Capacitance (f = 1.0 MHz)	C_C	—	0.1	—	pF
Diode Capacitance (V_R = 20 Vdc, f = 1.0 MHz)	C_T	—	—	1.0	pF

Reverse Voltage	V_R	200	Volts

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

DEVICE MARKING

MMBV3700 = 4R

CASE 318-02/03, STYLE 8
SOT-23 (TO-236AA/AB)

SILICON PIN SWITCHING DIODE

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I_R = 10 μA)	$V_{(BR)R}$	200	—	—	Volts
Diode Capacitance (Note 1) (V_R = 20 Vdc, f = 1.0 MHz)	C_T	—	—	1.0	pF
Series Resistance (Figure 5) (I_F = 10 mA)	R_S	—	0.4	1.0	Ohms
Reverse Leakage Current (V_R = 150 Vdc)	I_R	—	—	0.1	μA
Reverse Recovery Time (I_F = I_R = 10 mA)	t_{rr}	—	300	—	ns

NOTE:
1. C_T is measured using a capacitance bridge (Boonton Electronics Model 75A or equivalent).

3

TYPICAL ELECTRICAL CHARACTERISTICS

FIGURE 1 SERIES RESISTANCE

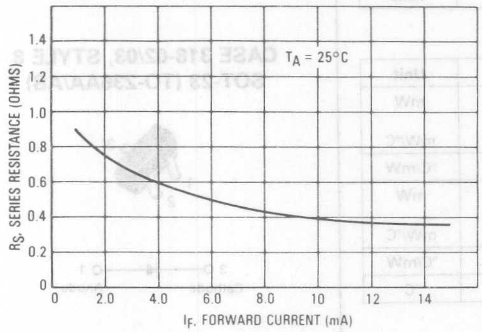


FIGURE 2 — FORWARD VOLTAGE

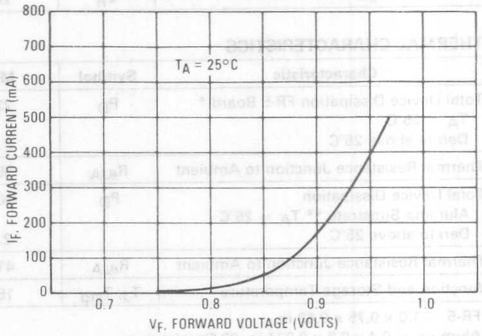


FIGURE 3 — DIODE CAPACITANCE

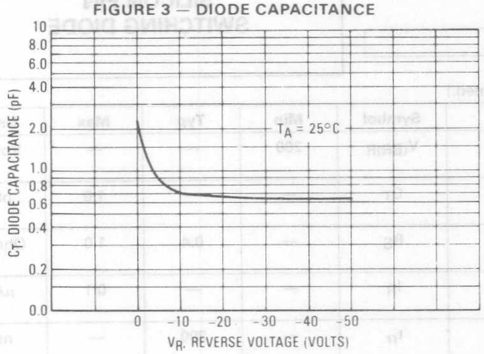


FIGURE 4 — LEAKAGE CURRENT

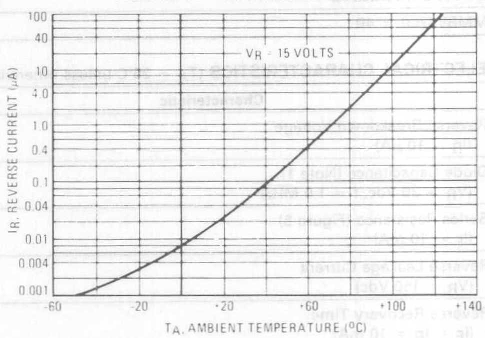
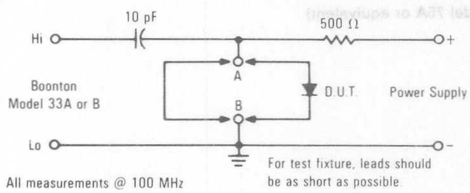


FIGURE 5 — FORWARD SERIES RESISTANCE TEST METHOD



To measure series resistance, a 10 pF capacitor is used to reduce the forward capacitance of the circuit and to prevent shorting of the external power supply through the bridge. The small signal from the bridge is prevented from shorting through the power supply by the 500-ohm resistor. The resistance of the 10 pF capacitor can be considered negligible for this measurement.

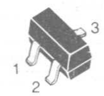
1. The RF Admittance Bridge (Boonton 33A or B) must be initially balanced, with the test circuit connected to the bridge test terminals. The conductance scale will be set at zero and the capacitance scale will be set at 120 pF, as required when using the 100 MHz test coil.
2. Use a short length of wire to short the test circuit from point "A" to "B". Then connect the power supply providing 10 mA of bias current to the test circuit.
3. Adjust the capacitance scale arm of the bridge and the "G" zero control for a minimum null on the "null meter". The null occurs at approximately 130 pF.
4. Replace the wire short with the device to be tested. Bias the device to a forward conductance state of 10 mA.
5. Obtain a minimum null on the "null meter", with the capacitance and conductance scale adjustment arms.
6. Read conductance (G) direct from the scale. Now read the capacitance value from the scale (≈130 pF) and subtract 120 pF which yields capacitance (C). The forward resistance (R_S) can now be calculated from:

$$R_S = \frac{2.533\ G}{C^2}$$

Where:
G — in micromhos,
C — in pF,
R_S — in ohms

MMBZ5226B thru MMBZ5257B

CASE 318-02/03, STYLE 8
SOT-23 (TO-236AA/AB)



ZENER DIODES

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/mW
Total Device Dissipation Alumina Substrate,** T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/mW
Junction and Storage Temperature	T_J, T_{stg}	150	°C

*FR-5 = 1.0 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

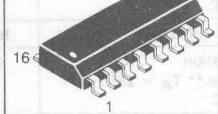
Pinout: 1-Anode, 2-NC, 3-Cathode (V_F = 0.9 V Max @ I_F = 10 mA for all types.)

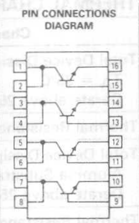
Device	Marking	Test Current I_{ZT} mA	Zener Voltage V_Z (±5%) Nominal	Z_{ZK} I_Z = 0.25 mA Ω Max	Z_{ZT} I_Z = I_{ZT} @ 10% Mod Ω Max	Max I_R µA @	V_R V
MMBZ5226B	8A	20	3.3	1600	28	25	1.0
MMBZ5227B	8B	20	3.6	1700	24	15	1.0
MMBZ5228B	8C	20	3.9	1900	23	10	1.0
MMBZ5229B	8D	20	4.3	2000	22	5.0	1.0
MMBZ5230B	8E	20	4.7	1900	19	5.0	2.0
MMBZ5231B	8F	20	5.1	1600	17	5.0	2.0
MMBZ5232B	8G	20	5.6	1600	11	5.0	3.0
MMBZ5233B	8H	20	6.0	1600	7.0	5.0	3.5
MMBZ5234B	8J	20	6.2	1000	7.0	5.0	4.0
MMBZ5235B	8K	20	6.8	750	5.0	3.0	5.0
MMBZ5236B	8L	20	7.5	500	6.0	3.0	6.0
MMBZ5237B	8M	20	8.2	500	8.0	3.0	6.5
MMBZ5238B	8N	20	8.7	600	8.0	3.0	6.5
MMBZ5239B	8P	20	9.1	600	10	3.0	7.0
MMBZ5240B	8Q	20	10	600	17	3.0	8.0
MMBZ5241B	8R	20	11	600	22	2.0	8.4
MMBZ5242B	8S	20	12	600	30	1.0	9.1
MMBZ5243B	8T	9.5	13	600	13	0.5	9.9
MMBZ5244B	8U	9.0	14	600	15	0.1	10
MMBZ5245B	8V	8.5	15	600	16	0.1	11
MMBZ5246B	8W	7.8	16	600	17	0.1	12
MMBZ5247B	8X	7.4	17	600	19	0.1	13
MMBZ5248B	8Y	7.0	18	600	21	0.1	14
MMBZ5249B	8Z	6.6	19	600	23	0.1	14
MMBZ5250B	81A	6.2	20	600	25	0.1	15
MMBZ5251B	81B	5.6	22	600	29	0.1	17
MMBZ5252B	81C	5.2	24	600	33	0.1	18
MMBZ5253B	81D	5.0	25	600	35	0.1	19
MMBZ5254B	81E	4.6	27	600	41	0.1	21
MMBZ5255B	81F	4.5	28	600	44	0.1	21
MMBZ5256B	81G	4.2	30	600	49	0.1	23
MMBZ5257B	81H	3.8	33	700	58	0.1	25

3

MMPQ2222
MMPQ2222A

CASE 751B-03
SO-16





QUAD GENERAL-PURPOSE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	MMPQ2222	MMPQ2222A	Unit
Collector-Emitter Voltage	V_{CEO}	30	40	Vdc
Collector-Base Voltage	V_{CB}	60	75	Vdc
Emitter-Base Voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
		Each Transistor	Four Transistors Equal Power	
Total Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.52 4.2	1.0 8.0	Watts mW/°C
Total Power Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	0.8 6.4	2.4 19.2	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	MMPQ2222 MMPQ2222A	$V_{(BR)CEO}$	30 40	— —	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	MMPQ2222 MMPQ2222A	$V_{(BR)CBO}$	60 75	— —	— —	Vdc
Emitter-Base Breakdown Voltage ($I_B = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	5.0 —	— —	— —	Vdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$) ($V_{CB} = 60$ Vdc, $I_E = 0$)	 MMPQ2222 MMPQ2222A	I_{CBO}	 — —	 — —	 50 10	nAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)	MMPQ2222 MMPQ2222A	I_{EBO}	— —	— —	50 10	nAdc
ON CHARACTERISTICS						
DC Current Gain(1) ($I_C = 100\ \mu$A, $V_{CE} = 10$ V) ($I_C = 1.0$ mA, $V_{CE} = 10$ V) ($I_C = 10$ mA, $V_{CE} = 10$ V) ($I_C = 150$ mA, $V_{CE} = 10$ V) ($I_C = 300$ mA, $V_{CE} = 10$ V) ($I_C = 500$ mA, $V_{CE} = 10$ V) ($I_C = 150$ mA, $V_{CE} = 1.0$ V)	 MMPQ2222A MMPQ2222A MMPQ2222 MMPQ2222A MMPQ2222 MMPQ2222A MMPQ2222 MMPQ2222A MMPQ2222A	h_{FE}	 35 50 75 75 100 100 30 40 50	 — — — — — — — — —	 — — — — — 300 — — —	
Collector-Emitter Saturation Voltage(1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 300$ mAdc, $I_B = 30$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	 MMPQ2222 MMPQ2222A MMPQ2222 MMPQ2222A	$V_{CE(sat)}$	 — — — —	 — — — —	 0.4 0.3 1.6 1.0	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 300$ mAdc, $I_B = 30$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	 MMPQ2222 MMPQ2222A MMPQ2222 MMPQ2222A	$V_{BE(sat)}$	 — — — —	 — — — —	 1.3 1.2 2.6 2.0	Vdc

ELECTRICAL CHARACTERISTICS (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS					
Current-Gain — Bandwidth Product(1) (I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	—	350	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{ob}	—	4.5	—	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)	C_{ib}	—	17	—	pF
SWITCHING CHARACTERISTICS					
Turn-On Time (V_{CC} = 30 Vdc, $V_{BE(off)}$ = 0.5 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_{on}	—	25	—	ns
Turn-Off Time (V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_{off}	—	250	—	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 2.0%.

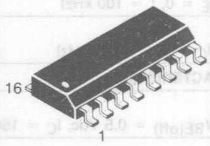
3

3

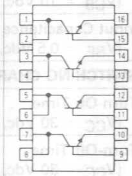
MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	15		Vdc
Collector-Base Voltage	V_{CB}	40		Vdc
Emitter-Base Voltage	V_{EB}	4.5		Vdc
Collector Current — Continuous	I_C	500		mAdc
		Each Transistor	Four Transistors Equal Power	
Total Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.4 3.2	0.72 6.4	Watts mW/°C
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	0.66 5.3	1.92 15.4	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

CASE 751B-03
SO-16



PIN CONNECTIONS DIAGRAM



QUAD SWITCHING TRANSISTOR

NPN SILICON

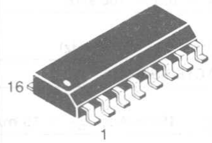
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

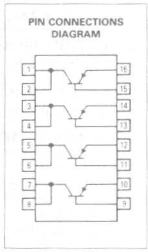
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	15	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	4.5 —	— —	— —	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0)	I_{CBO}	—	—	0.4	μAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)	I_{EBO}	—	—	0.5	μAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc) (I_C = 100 mAdc, V_{CE} = 2.0 Vdc)	h_{FE}	 40 20	 — —	 — —	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{CE(sat)}$	—	—	0.25	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{BE(sat)}$	—	—	0.9	Vdc
DYNAMIC CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	450	550	—	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 140 kHz)	C_{ob}	—	2.5	4.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 140 kHz)	C_{ib}	—	3.0	5.0	pF
SWITCHING CHARACTERISTICS					
Turn-On Time (V_{CC} = 3.0 Vdc, $V_{BE(off)}$ = 1.5 Vdc, I_C = 10 mAdc, I_{B1} = 3.0 mAdc)	t_{on}	—	9.0	—	ns
Turn-Off Time (V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = 3.0 mAdc, I_{B2} = 1.5 mAdc)	t_{off}	—	15	—	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 2.0%.

MMPQ2907A

CASE 751B-03
SO-16





QUAD GENERAL PURPOSE TRANSISTOR

PNP SILICON

3

MAXIMUM RATINGS

Rating	Symbol	MMPQ2907	MMPQ2907A	Unit
Collector-Emitter Voltage	V_{CEO}	40	60	Vdc
Collector-Base Voltage	V_{CB}	60		Vdc
Emitter-Base Voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous	I_C	600		mAdc

		Each Transistor	Four Transistors Equal Power	
Total Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.52 4.2	1.0 8.0	Watts mW/°C
Total Power Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	0.8 6.4	2.4 19.2	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	MMPQ2907 MMPQ2907A	$V_{(BR)CEO}$	40 60	— —	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)		$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	5.0 —	— —	— —	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$) ($V_{CB} = 50$ Vdc, $I_E = 0$)	 MMPQ2907 MMPQ2907A	I_{CBO}	 — —	 — —	 50 10	nAdc
Emitter Cutoff Current ($V_{CB} = 3.0$ Vdc, $I_C = 0$)		I_{EBO}	—	—	50	nAdc
ON CHARACTERISTICS						
DC Current Gain(1) ($I_C = 100\ \mu$Adc, $V_{CE} = 10$ V) ($I_C = 1.0$ mAdc, $V_{CE} = 10$ V) ($I_C = 10$ mAdc, $V_{CE} = 10$ V) ($I_C = 150$ mAdc, $V_{CE} = 10$ V) ($I_C = 300$ mAdc, $V_{CE} = 10$ V) ($I_C = 500$ mAdc, $V_{CE} = 10$ V)	 MMPQ2907A MMPQ2907A MMPQ2907/2907A MMPQ2907/2907A MMPQ2907/2907A MMPQ2907/2907A	h_{FE}	 75 100 75/100 100 30/50 50	 — — — — — —	 — — — 300 — —	—
Collector-Emitter Saturation Voltage(1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 300$ mAdc, $I_B = 30$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	 MMPQ2907 MMPQ2907 MMPQ2907A	$V_{CE(sat)}$	 — — —	 — — —	 0.4 1.6 1.6	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 300$ mAdc, $I_B = 30$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	 MMPQ2907 MMPQ2907 MMPQ2907A	$V_{BE(sat)}$	 — — —	 — — —	 1.3 2.6 2.6	Vdc

3

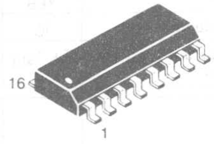
ELECTRICAL CHARACTERISTICS (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS					
Current-Gain — Bandwidth Product(1) (I_C = 50 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	—	350	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{ob}	—	6.0	—	pF
Input Capacitance (V_{BE} = 2.0 Vdc, I_C = 0, f = 100 kHz)	C_{ib}	—	20	—	pF
SWITCHING CHARACTERISTICS					
Turn-On Time (V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_{on}	—	30	—	ns
Turn-Off Time (V_{CC} = 6.0 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_{off}	—	100	—	ns

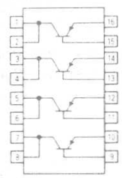
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 2.0%.

MMPQ3467

CASE 751B-03
SO-16



PIN CONNECTIONS DIAGRAM



3

QUAD MEMORY DRIVER TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CB}	40		Vdc
Emitter-Base Voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous	I_C	1.0		mAdc
		Each Transistor	Four Transistors Equal Power	
Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.52 4.2	1.2 9.6	Watts mW/°C
Power Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.0 8.0	2.5 20	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	5.0 —	— —	— —	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	—	200	nAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	200	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) ($I_C = 500$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	20	—	—	—
Collector-Emitter Saturation Voltage(1) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	$V_{CE(sat)}$	—	0.23	0.5	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	$V_{BE(sat)}$	—	0.9	1.2	Vdc
DYNAMIC CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	—	190	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{ob}	—	10	—	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz)	C_{ib}	—	55	—	pF
SWITCHING CHARACTERISTICS					
Turn-On Time ($I_C = 500$ mAdc, $I_{B1} = 50$ mAdc)	t_{on}	—	20	—	ns
Turn-Off Time ($I_C = 500$ mAdc, $I_{B1} = I_{B2} = 50$ mAdc)	t_{off}	—	60	—	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

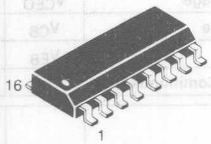
3

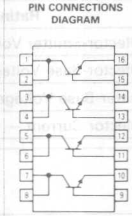
MAXIMUM RATINGS

Rating	Symbol	MMPQ3725	MMPQ3725A	Unit
Collector-Emitter Voltage	V_{CEO}	40	50	Vdc
Collector-Emitter Voltage	V_{CES}	60	70	Vdc
Emitter-Base Voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous	I_C	1.0		Adc
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

		Each Transistor	Four Transistors Equal Power	
Total Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.6 4.8	1.4 11.2	Watts mW/°C
Power Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.0 8.0	2.5 2.0	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

CASE 751B-03
SO-16





QUAD CORE DRIVER TRANSISTOR

NPN SILICON

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

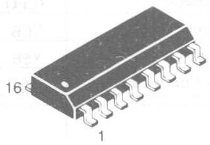
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	MMPQ3725 MMPQ3725A	$V_{(BR)CEO}$	40 50	— —	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $V_{BE} = 0$)	MMPQ3725 MMPQ3725A	$V_{(BR)CES}$	60 70	— —	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	5.0 —	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 40$ Vdc, $I_E = 0$)		I_{CBO}	—	—	0.5	μAdc
ON CHARACTERISTICS(1)						
DC Current Gain ($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 500$ mAdc, $V_{CE} = 2.0$ Vdc)	 MMPQ3725 MMPQ3725A MMPQ3725 MMPQ3725A	h_{FE}	 35 40 25 30	 75 80 45 50	 200 — — —	—
Collector-Emitter Saturation Voltage ($I_C = 500$ mAdc, $I_B = 50$ mAdc)		$V_{CE(sat)}$	—	0.32	0.45	Vdc
Base-Emitter Saturation Voltage ($I_C = 500$ mAdc, $I_B = 50$ mAdc)		$V_{BE(sat)}$	0.8	0.9	1.0	Vdc
DYNAMIC CHARACTERISTICS						
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	MMPQ3725 MMPQ3725A	f_T	—	275 250	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)		C_{ob}	—	5.1	—	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz)		C_{ib}	—	62	—	pF
SWITCHING CHARACTERISTICS						
Turn-On Time ($I_C = 500$ mAdc, $I_{B1} = 50$ mAdc, $V_{BE(off)} = 3.8$ Vdc)		t_{on}	—	20	—	ns
Turn-Off Time ($I_C = 500$ mAdc, $I_{B1} = I_{B2} = 50$ mAdc)		t_{off}	—	50	—	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

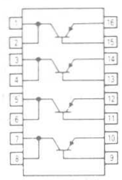
MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CB}	40		Vdc
Emitter-Base Voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous	I_C	1.5		mAdc
		Each Transistor	Four Transistors Equal Power	
Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.6 4.8	1.4 11	Watts mW/°C
Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0	2.5 20	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

CASE 751B-03
SO-16



PIN CONNECTIONS DIAGRAM



QUAD MEMORY DRIVER TRANSISTOR

PNP SILICON

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0 —	— —	— —	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	—	—	100	nAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)	I_{EBO}	—	—	100	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 150 mAdc, V_{CE} = 1.0 Vdc) (I_C = 500 mAdc, V_{CE} = 2.0 Vdc) (I_C = 1.0 Adc, V_{CE} = 2.0 Vdc)	h_{FE}	 35 30 20	 70 65 35	 — — —	—
Collector-Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc) (I_C = 1.0 Adc, I_B = 100 mAdc)	$V_{CE(sat)}$	 — —	 0.3 0.6	 0.55 0.9	Vdc
Base-Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc) (I_C = 1.0 Adc, I_B = 100 mAdc)	$V_{BE(sat)}$	 — —	 0.9 1.0	 1.25 1.4	Vdc
DYNAMIC CHARACTERISTICS					
Current-Gain — Bandwidth Product(1) (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	—	275	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{ob}	—	9.0	—	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)	C_{ib}	—	55	—	pF
SWITCHING CHARACTERISTICS					
Turn-On Time (V_{CC} = 30 Vdc, I_C = 1.0 Adc, I_{B1} = 100 mAdc, $V_{BE(off)}$ = 2.0 Vdc)	t_{on}	—	25	—	ns
Turn-Off Time (V_{CC} = 30 Vdc, I_C = 1.0 Adc, I_{B1} = I_{B2} = 100 mAdc)	t_{off}	—	60	—	ns

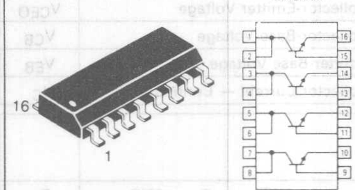
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

3

MMPQ3904

CASE 751B-03
SO-16

PIN CONNECTIONS DIAGRAM



QUAD AMPLIFIER/SWITCH TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CB}	60	Vdc
Emitter-Base Voltage	V_{EB}	6.0	Vdc
Collector Current — Continuous	I_C	200	mAdc

		Each Transistor	Four Transistors Equal Power	
Total Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.4 3.2	0.72 6.4	Watts mW/°C
Total Power Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	0.66 5.3	1.92 15.4	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

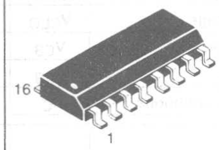
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	6.0 —	— —	— —	Vdc
Collector Cutoff Current ($V_{CB} = 40$ Vdc, $I_E = 0$)	I_{CBO}	—	—	50	nAdc
Emitter Cutoff Current ($V_{BE} = 4.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	50	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	 30 50 75	 90 160 200	 — — —	
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	0.1	0.2	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	—	0.65	0.85	Vdc
DYNAMIC CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)	f_T	250	300	—	MHz
Output Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 140 kHz)	C_{ob}	—	2.0	4.0	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 140 kHz)	C_{ib}	—	4.0	8.0	pF
SWITCHING CHARACTERISTICS					
Turn-On Time ($I_C = 10$ Vdc, $V_{BE(off)} = 0.5$ Vdc, $I_{B1} = 1.0$ mAdc)	t_{on}	—	37	—	ns
Turn-Off Time ($I_C = 10$ mAdc, $I_{B1} = I_{B2} = 1.0$ mAdc)	t_{off}	—	136	—	ns

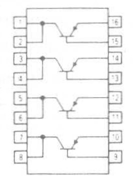
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MMPQ3906

CASE 751B-03
SO-16



PIN CONNECTIONS DIAGRAM



QUAD AMPLIFIER/SWITCH TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CB}	40		Vdc
Emitter-Base Voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
		Each Transistor	Four Transistors Equal Power	
Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.4 3.2	0.72 6.4	Watts mW/°C
Power Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	0.66 5.3	1.92 15.4	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

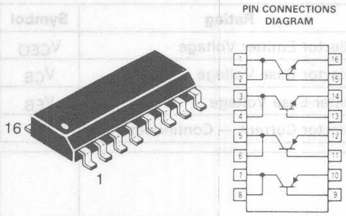
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	5.0 —	— —	— —	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	—	50	nAdc
Emitter Cutoff Current ($V_{BE} = 4.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	50	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	 40 60 75	 160 180 200	 — — —	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	0.1	0.25	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	—	0.65	0.85	Vdc
DYNAMIC CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)	f_T	200	250	—	MHz
Output Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 140 kHz)	C_{ob}	—	3.3	4.5	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 140 kHz)	C_{ib}	—	4.8	10	pF
SWITCHING CHARACTERISTICS					
Turn-On Time ($I_C = 10$ mAdc, $V_{BE(off)} = 0.5$ Vdc, $I_{B1} = 1.0$ mAdc)	t_{on}	—	43	—	ns
Turn-Off Time ($I_C = 10$ mAdc, $I_{B1} = I_{B2} = 1.0$ mAdc)	t_{off}	—	155	—	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CB}	40		Vdc
Emitter-Base Voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
		Each Transistor	**Four Transistors Equal Power**	
Total Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.4 3.2	0.72 6.4	Watts mW/°C
Total Power Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	0.66 5.3	1.92 15.4	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

CASE 751B-03
SO-16



QUAD COMPLEMENTARY PAIR TRANSISTORS

PNP/NPN SILICON

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	50	nAdc
Emitter Cutoff Current ($V_{EB} = 4.0$ Vdc, $I_C = 0$)	I_{EBO}	—	50	nAdc
ON CHARACTERISTICS(1)				
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	 30 50 70	 — — —	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	0.25	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	—	0.9	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain — Bandwidth Product(1) ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)	f_T	200	—	MHz
Output Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 100 kHz)	C_{ob}	—	4.5	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz) PNP NPN	C_{ib}	—	 10 8.0	pF

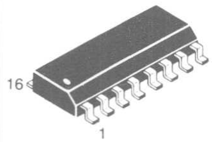
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

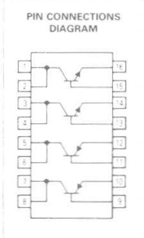
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CB}	30	Vdc
Emitter-Base Voltage	V_{EB}	4.0	Vdc
Collector Current — Continuous	I_C	200	mAdc

		Each Transistor	Four Transistors Equal Power	
Total Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.4 3.2	0.72 6.4	Watts mW/°C
Total Power Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	0.66 5.3	1.92 15.4	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

CASE 751B-03
SO-16





QUAD MPU CLOCK BUFFER TRANSISTORS

PNP/NPN SILICON

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

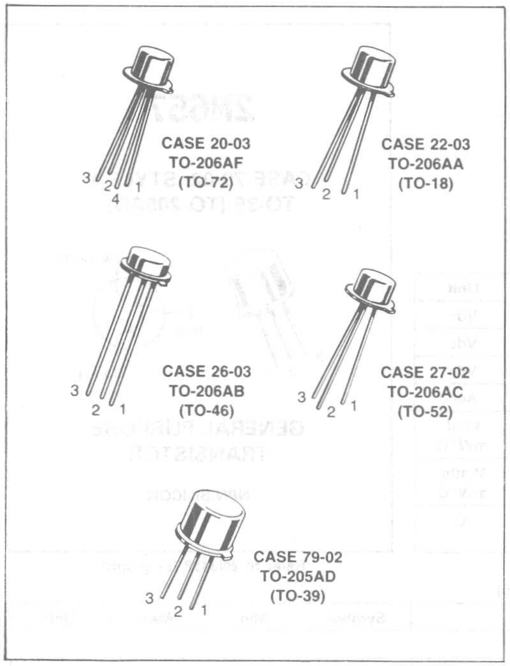
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	30	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$)	I_{CBO}	—	—	50	nAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	50	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 0.5$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	 30 50 70	 — —	 — —	—
Collector-Emitter Saturation Voltage ($I_C = 0.5$ mAdc, $I_B = 0.05$ mAdc, $0°C \leq T \leq 70°C$)	$V_{CE(sat)}$	—	0.05	0.15	Vdc
Base-Emitter Saturation Voltage ($I_C = 0.5$ mAdc, $I_B = 0.05$ mAdc)	$V_{BE(sat)}$	—	0.65	0.9	Vdc
DYNAMIC CHARACTERISTICS					
Current-Gain — Bandwidth Product(1) ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)	f_T	200	350	—	MHz
Output Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 100 kHz)	C_{ob}	—	3.0	4.5	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz) PNP NPN	C_{ib}	 — —	 5.0 4.0	 10 8.0	pF
SWITCHING CHARACTERISTICS ($T_A = 25°C$, $V_{CC} = 5.0$ Vdc)					
Propagation Delay Time (50% Points TP1 to TP3) (50% Points TP2 to TP4)	 t_{PLH} t_{PHL}	 — —	 15 6.0	 25 15	ns
Rise Time (0.3 V to 4.7 V, TP3 or TP4)	t_r	5.0	25	35	ns
Fall Time (4.7 V to 0.3 V, TP3 or TP4)	t_f	5.0	10	20	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

3

Metal Transistors

4



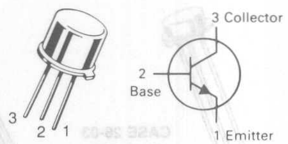
Motorola's metal-can transistor product offering includes: general purpose, switching, high voltage, choppers, Darlingtons, low noise amplifiers and RF amplifiers.

A variety of package options are available: TO-18, TO-46, TO-52, TO-72, and TO-39.

Many devices contained in this section are also available with high reliability MIL-S-19500 processing. JAN, JANTX, JANTXV, and JANS qualified devices are so noted on the following data sheets.

4

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N3498 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	100	Vdc
Collector-Base Voltage	V_{CBO}	100	Vdc
Emitter-Base Voltage	V_{EBO}	8.0	Vdc
Collector Current — Continuous	I_C	0.5	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 5.7	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	4.0 22.8	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

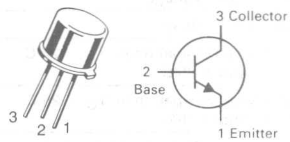
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 250\ \mu Adc$, $I_B = 0$)	$V_{(BR)CEO}$	100	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu Adc$, $I_E = 0$)	$V_{(BR)CBO}$	100	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 250\ \mu Adc$, $I_C = 0$)	$V_{(BR)EBO}$	8.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	10	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 200$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	30	90	—
Collector-Emitter Saturation Voltage(1) ($I_C = 200$ mAdc, $I_B = 40$ mAdc)	$V_{CE(sat)}$	—	4.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Input Impedance(1) ($I_B = 8.0$ mAdc, $V_{CE} = 10$ Vdc)	h_{fe}	—	0.5	k ohm

(1) Pulse Test: Pulse Length = 300 μs, Duty Cycle ≤ 2.0%.

2N697

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N2218 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CER}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.6 4.0	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.0 13.3	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

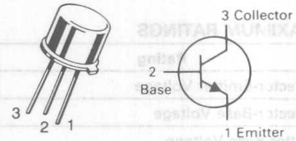
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 100$ mAdc, $R_{BE} = 10$ ohms)	$V_{(BR)CER}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$) ($V_{CB} = 30$ Vdc, $I_E = 0$, $T_A = 150°C$)	I_{CBO}	 — —	 1.0 100	μAdc
ON CHARACTERISTICS				
DC Current Gain(1) ($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	40	120	—
Collector-Emitter Saturation Voltage(1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{CE(sat)}$	—	1.5	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{BE(sat)}$	—	1.3	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$)	C_{obo}	—	35	pF
Small-Signal Current Gain ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)	h_{fe}	2.5	—	MHz

(1) Pulse Test: Pulse Length ≤ 12 ms, Duty Cycle ≤ 2.0%.

2N699

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N3019 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CER}	80	Vdc
Collector-Base Voltage	V_{CBO}	120	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.6 4.0	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.0 13.3	Watts mW/°C
Operating and Storage Temperature Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	75	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	250	°C/W

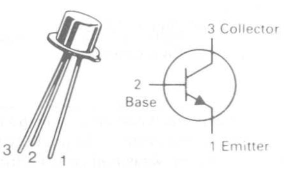
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (1) ($I_C = 100$ mAdc, $R_{BE} \leq 10$ ohms)	$V_{(BR)CER}$	80	—	Vdc
Collector Cutoff Current ($V_{CB} = 60$ Vdc, $I_E = 0$) ($V_{CB} = 60$ Vdc, $I_E = 0$, $T_A = 150°C$)	I_{CBO}	—	2.0 200	μAdc
Emitter Cutoff Current ($V_{EB} = 2.0$ Vdc, $I_C = 0$)	I_{EBO}	—	100	μAdc
ON CHARACTERISTICS				
DC Current Gain (1) ($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	40	120	—
Collector-Emitter Saturation Voltage (1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{CE(sat)}$	—	5.0	Vdc
Base-Emitter Saturation Voltage (1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{BE(sat)}$	—	1.3	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)	f_T	50	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	20	pF
Input Impedance ($I_C = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CB} = 10$ Vdc, f = 1.0 kHz)	h_{ib}	20	30 10	Ohms
Voltage Feedback Ratio ($I_C = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CB} = 10$ Vdc, f = 1.0 khZ)	h_{rb}	— —	2.5 3.0	X 10^{-4}
Small Signal Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	35 45	100 —	—
Output Admittance ($I_C = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CB} = 10$ Vdc, f = 1.0 kHz)	h_{ob}	0.05 —	0.5 1.0	μmhos

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2N706,A,B

(2N706 JAN AVAILABLE)
CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

NPN SILICON

Refer to 2N2368 for graphs.

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector-Emitter Voltage	2N706A,B	V_{CEO}	15	Vdc
Collector-Emitter Voltage(1)		V_{CER}	20	Volts
Collector-Base Voltage		V_{CBO}	25	Volts
Emitter-Base Voltage	2N706 2N706A 2N706B	V_{EBO}	3.0 5.0 5.0	Volts
Collector Current	2N706,A,B	I_C	50	mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C		P_D	0.3 2.0	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C		P_D	1.0 6.67	Watts mW/°C
Total Device Dissipation @ $T_C = 100°C$ Derate above 100°C		P_D	0.5	Watt
Operating and Storage Junction Temperature Range		T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	150	°C/W
Thermal Resistance, Junction to Ambient 2N706A,B	$R_{\theta JA}$	500	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	15	—	Vdc
Collector-Emitter Breakdown Voltage(2) (R = 10 ohms, $I_C = 10$ mAdc)		$V_{(BR)CER}$	20	—	Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_E = 0$) ($V_{CB} = 15$ Vdc, $I_E = 0$, $T_A = 150°C$) ($V_{CB} = 25$ Vdc, $I_E = 0$)	 2N706A, 2N706B	I_{CBO}	 — — —	 0.5 30 10	μAdc
Collector Cutoff Current ($V_{CE} = 20$ Vdc, $R_{BE} = 100k$)	 2N706A, 2N706B	I_{CER}	—	10	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$) ($V_{EB} = 5.0$ Vdc, $I_C = 0$)	 2N706 2N706A, 2N706B	I_{EBO}	 — —	 10 10	μAdc
ON CHARACTERISTICS					
DC Current Gain(2) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc)	 2N706 2N706A, 2N706B	h_{FE}	 20 20	 — 60	—
Collector-Emitter Saturation Voltage(2) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	 2N706, 2N706A 2N706B	$V_{CE(sat)}$	 — —	 0.6 0.4	Vdc
Base-Emitter Saturation Voltage(2) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	 2N706 2N706A, 2N706B	$V_{BE(sat)}$	 — 0.7	 0.9 0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($V_{CE} = 15$ Vdc, $I_E = 10$ mAdc, f = 100 MHz)		f_T	200	—	MHz
Output Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$) ($V_{CB} = 10$ Vdc, $I_E = 0$)	 2N706A, 2N706B 2N706	C_{obo}	 — —	 5.0 6.0	pF
Magnitude of Forward Current Transfer Ratio, Common-Emitter ($V_{CE} = 15$ Vdc, $I_E = 10$ mAdc, f = 100 Mhz) ($V_{CE} = 10$ Vdc, $I_E = 10$ mAdc, f = 100 MHz)	 2N706 2N706A,B	$\|h_{fe}\|$	 2.0 2.0	 — —	—

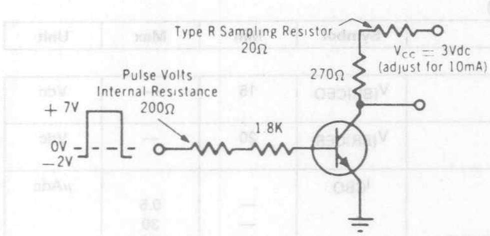
4

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

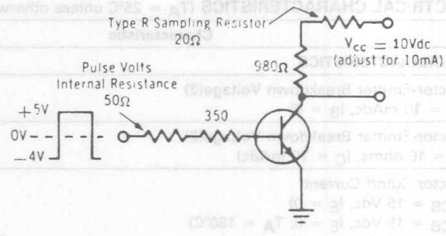
Characteristic		Symbol	Min	Max	Unit
Collector Base Time Constant (V_{CE} = 15 Vdc, I_E = 10 mAdc, f = 300 MHz)		r_b	—	50	ohms
Storage Time	2N706B	t_s	—	25	ns
Turn-On Time (I_{B1} = 3.0 mA, I_{B2} = 1.0 mA)		t_{on}	—	40	ns
Turn-Off Time (I_{B1} = 3.0 mA, I_{B2} = 1.0 mA)		t_{off}	—	75	ns
Charge Storage Time Constant(2)	2N706	τ_s	—	60	ns
	2N706A,B		—	25	

(1) Refers to collector breakdown voltage in the high current region when R_{be} = 10 Ω
(2) Pulse Test: Pulse Width ≤ 12 μs, Duty Cycle ≤ 2.0%.
(3) Switching Times Measured with Tektronix Type R Plug-In (50 Ω Internal Impedance).

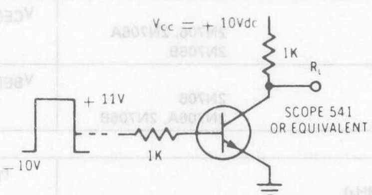
SWITCHING TIME TEST CIRCUIT



STORAGE TIME TEST CIRCUIT

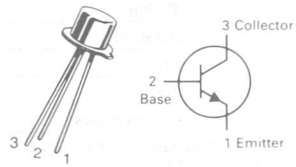


MEASUREMENT CIRCUIT



2N708

JAN, JTX AVAILABLE
CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

NPN SILICON

Refer to 2N2368 for graphs.

4

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Emitter Voltage	V_{CER}	20	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	limited by P_D only	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	360 2.1	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ $T_C = 100°C$ Derate above 25°C Derate above 100°C	P_D	1.2 680 6.9 6.9	Watts mW mW/°C mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

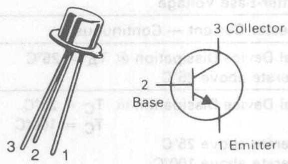
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	145	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 30$ mAdc, $R_{BE} \leq 10$ ohms)	$V_{CER(sus)}$	20	—	Vdc
Collector-Emitter Sustaining Voltage ($I_C = 30$ mAdc, $I_B = 0$)	$V_{CEO(sus)}$	15	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 1.0\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 20$ Vdc, $V_{BE} = 0.25$ Vdc, $T_A = +125°C$)	I_{CEX}	—	10	μAdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$) ($V_{CB} = 20$ Vdc, $I_C = 0$, $T_A = 150°C$)	I_{CBO}	— —	0.025 15	μAdc
Emitter Cutoff Current ($V_{BE} = 4.0$ Vdc, $I_C = 0$)	I_{EBO}	—	0.08	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 0.5$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc)(1) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc, $T_A = -55°C$)(1)	h_{FE}	 15 30 15	 — 120 —	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 7.0$ mAdc, $I_B = 0.7$ mAdc, $T_A = -55°C$ to $+125°C$)	$V_{CE(sat)}$	 — —	 0.4 0.4	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 7.0$ mAdc, $I_B = 0.7$ mAdc, $T_A = -55°C$)	$V_{BE(sat)}$	 0.72 —	 0.80 0.90	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	300	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, 100 kHz ≤ f ≤ 1.0 MHz)	C_{obo}	—	6.0	pF
Extrinsic Base Resistance ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 300 MHz)	r_b'	—	50	ohms
SWITCHING CHARACTERISTICS				
Storage Time ($I_C = I_{B1} = I_{B2} = 10$ mAdc)	t_s	—	25	ns
Turn-On Time	t_{on}	—	40	ns
Turn-Off Time	t_{off}	—	70	ns

2N718

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N2218 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage(1)	V_{CER}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	500	mA
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.4 2.66	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 10	Watts mW/°C
Total Device Dissipation @ T_C = 100°C	P_D	0.75	Watt
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +175	°C

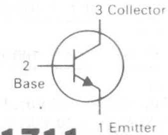
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 100 mAdc, pulsed; $R_B \le 10$ Ohms)	$V_{CER(sus)}$	40	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 1.0 mA, I_C = 0)	$V_{(BR)EBO}$	5	—	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0) (V_{CB} = 30 Vdc, I_E = 0, T_A = 150°C)	I_{CBO}	 — —	 1.0 100	μAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 150 mAdc, V_{CE} = 10 Vdc)	h_{FE}	40	120	—
Collector-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{CE(sat)}$	—	1.5	Vdc
Base-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{BE(sat)}$	—	1.3	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance (V_{CB} = 10 Vdc, f = 100 kHz, I_E = 0)	C_{obo}	—	35	pF
Input Capacitance (V_{BE} = 0.5 V, f = 100 kHz, I_C = 0)	C_{ibo}	—	80	pF
Small-Signal Current Gain (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)	h_{fe}	2.5	—	—

(1) Pulse Test: PW ≤ 300 μs, Duty Cycle ≤ 2.0%.

2N718A
2N956

CASE 22-03, STYLE 1
TO-18 (TO-206AA)
2N718A JAN, JTX,
JTXV AVAILABLE



2N1711

CASE 79-02, STYLE 1
TO-39 (TO-205AD)

GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N3019 for graphs.*

4

MAXIMUM RATINGS

Rating	Symbol	2N718A 2N956	2N1711	Unit
Collector-Emitter Voltage	V_{CER}	50		Vdc
Collector-Base Voltage	V_{CBO}	75		Vdc
Emitter-Base Voltage	V_{EBO}	7.0		Vdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	500 2.86	800 4.57	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.8 10.3	3.0 17.15	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

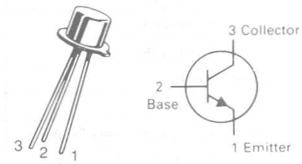
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 100 mAdc, pulsed; $R_{BE} \leq 10$ ohms)	$V_{CER(sus)}$	50	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	75	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	7.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 60 Vdc, I_E = 0) (V_{CB} = 60 Vdc, I_E = 0, T_A = 150°C)	I_{CBO}	 — —	 0.001 —	 0.01 10	μAdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0) 2N718A, 2N956, 2N1711	I_{EBO}	 — —	 — —	 0.010 0.005	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 0.01 mAdc, V_{CE} = 10 Vdc) 2N956, 2N1711	h_{FE}	 20	 —	 —	—
(I_C = 0.1 mAdc, V_{CE} = 10 Vdc) 2N718A, 2N956, 2N1711		20 35	— —	— —	
(I_C = 10 mAdc, V_{CE} = 10 Vdc) 2N718A, 2N956, 2N1711		35 75	— —	— —	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, T_A = −55°C) 2N718A, 2N956, 2N1711		20 35	— —	— —	
(I_C = 150 mAdc, V_{CE} = 10 Vdc) 2N718A, 2N956, 2N1711		40 100	— —	120 300	
(I_C = 500 mAdc, V_{CE} = 10 Vdc) 2N718A, 2N956, 2N1711		20 40	— —	— —	
Collector-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{CE(sat)}$	—	0.24	1.5	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{BE(sat)}$	—	1.0	1.3	Vdc

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

Characteristic		Symbol	Min	Typ	Max	Unit
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)	2N718A, 2N956, 2N1711	f_T	60 70	300 300	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	4.0	25	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	20	80	pF
Input Impedance (I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz) (I_C = 5.0 mAdc, V_{CB} = 10 Vdc, f = 1.0 kHz)		h_{ib}	24 4.0	— —	34 8.0	ohms
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)	2N718A, 2N956, 2N1711	h_{rb}	— —	— —	3.0 5.0	$\times 10^{-4}$
(I_C = 5.0 mAdc, V_{CB} = 10 Vdc, f = 1.0 kHz)	2N718A, 2N956, 2N1711		— —	— —	3.0 5.0	
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	2N718A, 2N956, 2N1711	h_{fe}	30 50	— —	100 200	—
(I_C = 5.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N718A, 2N956, 2N1711		35 70	— —	150 300	
Output Admittance (I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz) (I_C = 5.0 mAdc, V_{CB} = 10 Vdc, f = 1.0 kHz)		h_{ob}	0.05 0.05	— —	0.5 0.5	µmhos
Noise Figure (I_C = 300 µAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N718A, 2N956, 2N1711	NF	— —	— —	12 8.0	dB

2N720A

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N3019 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	80	Vdc
Collector-Emitter Voltage	V_{CER}	100	Vdc
Collector-Base Voltage	V_{CBO}	120	Vdc
Emitter-Base Voltage	V_{EBO}	7.0	Vdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.5 2.86	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.8 10.3	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	97	°C/W

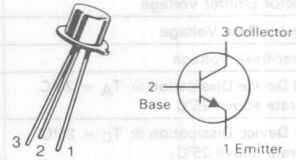
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 100$ mAdc, $R_{BE} \leq 10$ ohms)	$V_{CER(sus)}$	100	—	Vdc
Collector-Emitter Sustaining Voltage(1) ($I_C = 30$ mAdc, $I_B = 0$)	$V_{CEO(sus)}$	80	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	120	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	7.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 90$ Vdc, $I_E = 0$) ($V_{CB} = 90$ Vdc, $I_E = 0$, $T_A = 150°C$)	I_{CBO}	— —	.010 15	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$)	I_{EBO}	—	.010	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc)(1) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, $T_A = -55°C$) ($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)(1)	h_{FE}	20 35 20 40	— — — 120	—
Collector-Emitter Saturation Voltage(1) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc) ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{CE(sat)}$	— —	1.2 5.0	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc) ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{BE(sat)}$	— —	0.9 1.3	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)	f_T	50	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	15	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz)	C_{ibo}	—	85	pF
Input Impedance ($I_C = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CB} = 10$ Vdc, f = 1.0 kHz)	h_{ib}	20 4.0	30 8.0	Ohms
Voltage Feedback Ratio ($I_C = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CB} = 10$ Vdc, f = 1.0 kHz)	h_{rb}	— —	1.25 1.50	$X\ 10^{-4}$
Small-Signal Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	30 45	100 —	—
Output Admittance ($I_C = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CB} = 10$ Vdc, f = 1.0 kHz)	h_{ob}	— —	0.5 0.5	μmhos

(1) Pulse Test: Pulse Width $\leq 300\ \mu$s, Duty Cycle $\leq 2.0\%$.

2N834
2N835

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

NPN SILICON

Refer to 2N2368 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	20	Vdc
Collector-Emitter Voltage	V_{CES}	30	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous Peak	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.3 2.0	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.0 6.67	Watts mW/°C
Total Device Dissipation @ $T_C = 100°C$ Derate above 100°C	P_D	0.5 6.67	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +175	°C

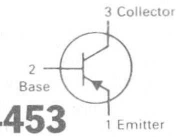
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0) (V_{CB} = 20 Vdc, I_E = 0, T_A = 150°C)	I_{CBO}	 — —	 0.5 30	μAdc
Collector Cutoff Current (V_{CE} = 30 Vdc, V_{BE} = 0)	I_{CES}	—	10	μAdc
ON CHARACTERISTICS				
DC Current Gain(1) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	h_{FE}	25	—	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)	$V_{CE(sat)}$	 — —	 0.25 0.4	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 15 Vdc, f = 100 MHz)	f_T	350	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	4.0	pF
Magnitude of Forward Current Transfer Ratio, Common-Emitter (I_C = 10 mAdc, V_{CE} = 15 Vdc, f = 100 MHz)	$\lvert h_{fe}\rvert$	3.5	—	—
SWITCHING CHARACTERISTICS				
Charge-Storage Time Constant (Figure 2) (I_C = 10 mAdc, I_{B1} = I_{B2} = 10 mAdc)	t_s	—	25	ns
Turn-On Time (Figure 1) (I_C = 10 mAdc, I_{B1} = 3.0 mAdc, I_{B2} = 1.0 mAdc)	t_{on}	—	35	ns
Turn-Off Time (Figure 1) (I_C = 10 mAdc, I_{B1} = 3.0 mAdc, I_{B2} = 1.0 mAdc)	t_{off}	—	75	ns

(1) Pulse Test: Pulse Width ≤ 12 ms, Duty Cycle ≤ 2.0%.

2N869A

JAN, JTX, JTXV AVAILABLE
CASE 22-03, STYLE 1
TO-18 (TO-206AA)



2N4453

CASE 26-03, STYLE 1
TO-46 (TO-206AB)
JAN, JANTX AVAILABLE

SWITCHING TRANSISTOR

PNP SILICON

4

MAXIMUM RATINGS

Rating	Symbol	2N869A	2N4453	Unit
Collector-Emitter Voltage	V_{CEO}	18	18	Vdc
Collector-Emitter Voltage	V_{CES}	25		Vdc
Collector-Base Voltage	V_{CBO}	25	25	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	360 2.06	400 2.29	mW mW/°C
Total Device Dissipation @ T_C = 25°C TC = 100°C Derate above 25°C	P_D	1.2 0.686 6.86	2.0 1.03 11.3	Watts Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	2N869A	2N4453	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	146	97.5	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	486	585	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	2N4453	$V_{(BR)CEO}$	18	—	Vdc
Collector-Emitter Breakdown Voltage (I_C = 10 μAdc, V_{BE} = 0)	2N869A, 2N4453	$V_{(BR)CES}$	25	—	Vdc
Collector-Emitter Sustaining Voltage(1) (I_C = 10 mAdc, I_B = 0)		$V_{CEO(sus)}$	18	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	2N869A, 2N4453	$V_{(BR)CBO}$	25	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 15 Vdc, I_E = 0, T_A = 150°C)	2N869A	I_{CBO}	—	25	μAdc
Collector Cutoff Current (V_{CE} = 15 Vdc, V_{BE} = 0)		I_{CES}	—	10	nAdc
Emitter Cutoff Current (V_{EB} = 4.5 Vdc, I_C = 0)	2N4453	I_{EBO}	—	10	nAdc
Base Current (V_{CE} = 15 Vdc, V_{BE} = 0)	2N869A	I_B	—	10	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 10 mAdc, V_{CE} = 0.3 Vdc) (I_C = 10 mAdc, V_{CE} = 5.0 Vdc) (I_C = 30 mAdc, V_{CE} = 0.5 Vdc) (I_C = 30 mAdc, V_{CE} = 0.5 Vdc, T_A = −55°C) (I_C = 100 mAdc, V_{CE} = 1.0 Vdc)	 2N869A 2N869A 2N869A, 2N4453 2N869A, 2N4453 2N869A, 2N4453	h_{FE}	 30 40 40 17 25	 — 120 120 — —	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 30 mAdc, I_B = 1.5 mAdc) (I_C = 30 mAdc, I_B = 3.0 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc)	 2N869A 2N4453 2N869A 2N869A, 2N4453	$V_{CE(sat)}$	 — — — —	 0.15 0.25 0.2 0.5	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 30 mAdc, I_B = 1.5 mAdc) (I_C = 30 mAdc, I_B = 3.0 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc)	 2N869A 2N4453 2N869A 2N869A, 2N4453	$V_{BE(sat)}$	 0.78 0.8 0.85 —	 0.98 1.1 1.2 1.7	Vdc

Characteristic		Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(1)(2) (I_C = 10 mAdc, V_{CE} = 15 Vdc, f = 100 MHz)		f_T	400		MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 140 kHz)	2N869A	C_{obo}	—	6.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 150 kHz)	2N869A	C_{ibo}	—	6.0	pF
Collector-Base Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	2N4453	C_{cb}	—	6.0	pF
Emitter-Base Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	2N4453	C_{eb}	—	6.0	pF

SWITCHING CHARACTERISTICS

Characteristic	Conditions		Symbol	Min	Max	Unit
Turn-On Time	I_C = 30 mAdc, I_{B1} = 1.5 mAdc	V_{CC} = 2.0 Vdc, 2N869A	t_{on}	—	50	ns
Delay Time		V_{CC} = 3.0 Vdc 2N4453	t_d	—	35	ns
Rise Time		V_{CC} = 3.0 Vdc 2N4453	t_r	—	20	ns
Turn-Off Time	I_C = 30 mAdc, I_{B1} = I_{B2} = 1.5 mAdc	V_{CC} = 2.0 Vdc 2N869A	t_{off}	—	80	ns
Storage Time		V_{CC} = 3.0 Vdc 2N4453	t_s	—	65	ns
Fall Time		V_{CC} = 3.0 Vdc 2N4453	t_f	—	20	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 1.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

TYPICAL SWITCHING CHARACTERISTICS

FIGURE 1 — CAPACITANCE

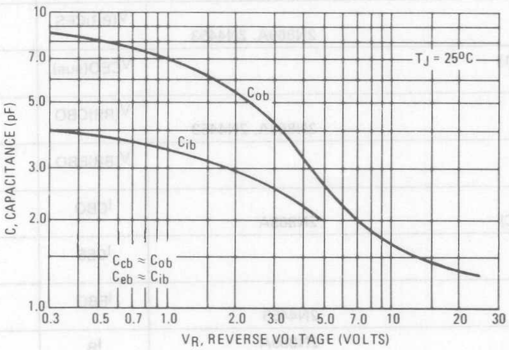


FIGURE 2 — DC CURRENT GAIN

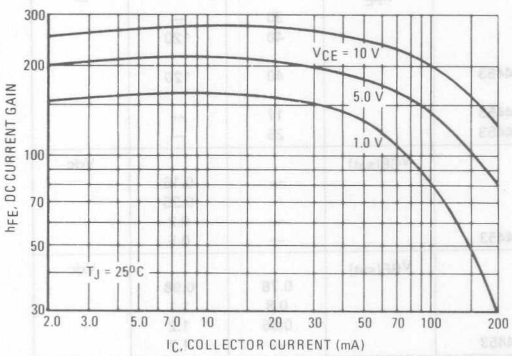


FIGURE 3 — "ON" VOLTAGES

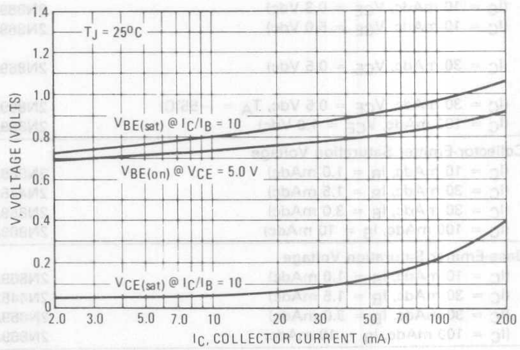


FIGURE 4 — CURRENT-GAIN — BANDWIDTH PRODUCT

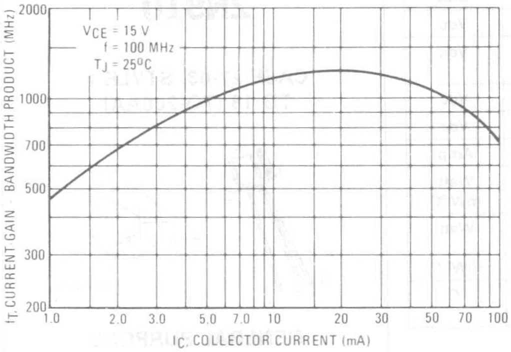


FIGURE 5 — TURN-ON TIME

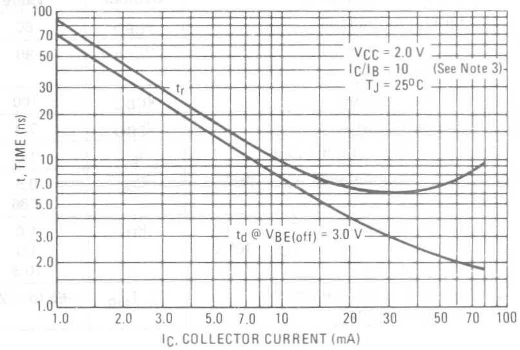


FIGURE 6 — TURN-OFF TIME

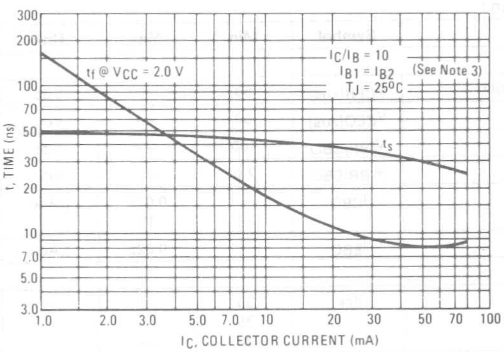


FIGURE 7 — SWITCHING TIME TEST CIRCUIT

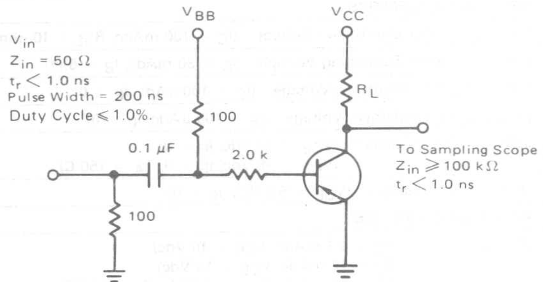


FIGURE 8 — SWITCHING TEST CIRCUIT VALUES

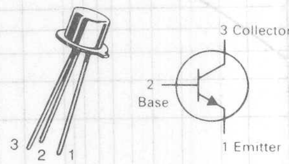
		V_{in} Volts	V_{BB} Volts	V_{CC} Volts	R_L Ohms	I_C mA	I_{B1} (4) mA	I_{B2} (4) mA
t_{on}, t_r, t_d	2N869A	-7.0	3.0	2.0	62	30	1.5	—
	2N4453	-7.0	3.0	3.0	91	30	1.5	—
t_{off}, t_s, t_f	2N869A	+6.0	-4.0	2.0	62	30	1.5	1.5
	2N4453	+6.0	-4.0	3.0	91	30	1.5	1.5

(3) I_C/I_B = 10. Switching is shown to reflect current industry practices. Compare the values shown in Figures 1 and 2 @ I_C = 30 mA to the typical values in the Electrical Characteristics table @ I_C/I_B = 20.

(4) $I_{B1} = I_{B2}$ = 3.0 mA @ I_C/I_B = 10

2N910

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N3019 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	60	Vdc
Collector-Emitter Voltage (R_{BE} = 10 Ohms)	V_{CER}	80	Vdc
Collector-Base Voltage	V_{CBO}	100	Vdc
Emitter-Base Voltage	V_{EBO}	7.0	Vdc
Collector Current — Continuous	I_C	1.0	Amp
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.5 2.86	Watt mW/°C
Total Device Dissipation @ T_C = 25°C T_C = 100°C Derate above 25°C	P_D	1.8 1.0 10.3	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	97.4	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	350	°C/W

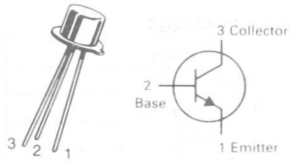
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 100 mAdc, R_{BE} ≤ 10 ohms)(1)	$V_{CER(sus)}$	80	—	Vdc
Collector-Emitter Sustaining Voltage (I_C = 30 mAdc, I_B = 0)(1)	$V_{CEO(sus)}$	60	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	100	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	7.0	—	Vdc
Collector Cutoff Current (V_{CB} = 75 Vdc, I_E = 0) (V_{CB} = 75 Vdc, I_E = 0, T_A = 150°C)	I_{CBO}	— —	0.025 15	μAdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)	I_{EBO}	—	0.025	μAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 0.1 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc, T_A = −55°C)	h_{FE}	35 75 30	— — —	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)	$V_{CE(sat)}$	— —	0.4 1.2	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)	$V_{BE(sat)}$	0.6 —	0.8 0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)	f_T	60	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	15	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)	C_{ibo}	—	85	pF
Input Impedance (I_C = 5.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{ie}	—	1800	Ohms
Input Impedance (I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz) (I_C = 5.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)	h_{ib}	20 4.0	30 8.0	Ohms
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)	h_{rb}	—	3.0	$X\ 10^{-4}$
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{fe}	76	200	—
Output Admittance (I_C = 5.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{oe}	—	100	μmhos
Output Admittance (I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz) (I_C = 5.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)	h_{ob}	— —	0.5 1.0	μmho
Noise Figure (I_C = 0.3 mAdc, V_{CB} = 10 Vdc, R_G = 510 ohms, f = 1.0 kHz, B W = 200 Hz)	NF	—	12	dB

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 2.0%.

2N914

JAN, JTX AVAILABLE
CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

NPN SILICON

Refer to 2N2368 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Emitter Voltage ($R_{BE} \leq 10$ ohms)	V_{CER}	20	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous(1)	I_C	150	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	360 2.06	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.2 6.8	Watts mW/°C
Total Device Dissipation @ $T_C = 100°C$ Derate above 100°C	P_D	0.68	Watt
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

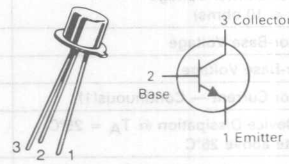
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(2) ($I_C = 30$ mAdc, $R_{BE} \leq 10$ ohms)	$V_{CER(sus)}$	20	—	Vdc
Collector-Emitter Sustaining Voltage(2) ($I_C = 30$ mAdc, $I_B = 0$)	$V_{CEO(sus)}$	15	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 1.0$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 20$ Vdc, $V_{BE} = 0.25$ Vdc, $T_A = 125°C$)	I_{CEX}	—	10	μAdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$) ($V_{CB} = 20$ Vdc, $I_E = 0$, $T_A = 150°C$)	I_{CBO}	— —	0.025 15	μAdc
Emitter Cutoff Current ($V_{BE} = 4.0$ Vdc, $I_C = 0$)	I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain(2) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc, $T_A = -55°C$) ($I_C = 500$ mAdc, $V_{CE} = 5.0$ Vdc)	h_{FE}	 30 12 10	 120 — —	—
Collector-Emitter Saturation Voltage(2) ($I_C = 200$ mAdc, $I_B = 20$ mAdc) ($I_C = 10$ mAdc, $I_B = 1.0$ thru 20 mAdc, $T_A = -55$ to $+125°C$)	$V_{CE(sat)}$	 — —	 0.70 0.25	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	0.70	0.80	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 20$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	300	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{obo}	—	6.0	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)	C_{ibo}	—	9.0	pF
SWITCHING CHARACTERISTICS				
Storage Time(3) ($I_C = I_{B1} = I_{B2} = 20$ mAdc)	t_s	—	20	ns
Turn-On Time(3) ($I_C = 200$ mAdc, $I_{B1} = 40$ mAdc, $I_{B2} = 20$ mAdc)	t_{on}	—	40	ns
Turn-Off Time(3) ($I_C = 200$ mAdc, $I_{B1} = 40$ mAdc, $I_{B2} = 20$ mAdc)	t_{off}	—	40	ns

(1) Limited by Power Dissipation.
(2) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 1.0%.
(3) Measured on Sampling Scope: Pulse Width ≥ 200 ns.

2N915

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N3946 for graphs.

MAXIMUM RATINGS

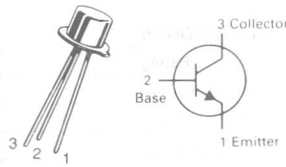
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector-Base Voltage	V_{CBO}	70	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.36 2.05	Watts mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.2 6.81	Watts mW/°C
Total Power Dissipation @ + 100°C Case	P_D	0.68	W
Operating and Storage Temperature Temperature Range	T_J, T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage(1) ($I_C = 10$ mA $I_B = 0$)	$V_{CEO(sus)}$	50	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μA $I_E = 0$)	$V_{(BR)CBO}$	70	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μA, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 60$ V, $I_E = 0$)	I_{CBO}	—	0.010	μA
Collector Cutoff Current ($V_{CB} = 60$ V, $I_E = 0$) ($V_{CB} = 60$ V, $I_E = 0$, $T_A = +150°C$)	I_{CBO}	 — —	 0.010 30	μA
ON CHARACTERISTICS				
DC Current Gain ($I_C = 10$ mA $V_{CE} = 5.0$ V)	h_{FE}	50	200	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mA $I_B = 1.0$ mA	$V_{CE(sat)}$	—	1.0	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mA $I_B = 1.0$ mA)	$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance ($I_E = 0$ $V_{CB} = 10$ V, f = 100 kHz)	C_{obo}	—	3.5	pF
Emitter Transition Capacitance ($I_C = 0$ $V_{EB} = 0.5$ V, f = 100 kHz)	C_{TE}	—	10	pF
Input Impedance ($I_C = 1.0$ mA $V_{CE} = 5.0$ V) ($I_C = 5.0$ mA $V_{CE} = 5.0$ V)	h_{ie}	 — —	 6000 2000	ohms
High Frequency Current Gain f = 100 MHz ($I_C = 10$ mA $V_{CE} = 15$ V)	h_{fe}	2.5	—	
Small-Signal Current Gain f = 1 kHz ($I_C = 1.0$ mA $V_{CE} = 5.0$ V) ($I_C = 5.0$ mA $V_{CE} = 5.0$ V)	h_{fe}	 40 50	 200 250	
Output Admittance ($I_C = 1.0$ mA $V_{CE} = 5.0$ V) ($I_C = 5.0$ mA $V_{CE} = 5.0$ V)	h_{oe}	 — —	 75 125	 μmhos μmho
Collector Base Time Constant ($I_C = 10$ mA, $V_{CB} = 10$ V, f = 40 mHz)	$rb'C_C$	—	300	ps

(1) Pulse Test: PW ≤ 300 μs, Duty Cycle ≤ 1.0%.

JAN AVAILABLE
CASE 22-03, STYLE 1
TO-18 (TO-206AA)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N3946 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	45	Vdc
Emitter-Base Voltage	V_{EBO}	5	Vdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.36 2.06	Watts mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.2 6.9	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage(1) ($I_C = 30$ mA, $I_B = 0$)	$V_{CEO(sus)}$	25	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μA, $I_E = 0$)	$V_{(BR)CBO}$	45	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μA, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ V, $I_E = 0$)	I_{CBO}	—	10	nAdc
Collector Cutoff Current @ 150°C ($V_{CB} = 30$ V, $I_E = 0$)	I_{CBO}	—	10	μAdc
ON CHARACTERISTICS				
DC Current Gain(1) ($I_C = 10$ mA, $V_{CE} = 1.0$ V) ($I_C = 10$ mA, $V_{CE} = 1.0$ V, −55°C)	h_{FE}	 50 15	 200 —	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 1.0$ mA)	$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 1.0$ mA)	$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance ($V_{CB} = 5.0$ V, $I_E = 0$)	C_{obo}	—	6.0	pF
Input Capacitance ($V_{EB} = 0.5$ V, $I_C = 0$)	C_{ibo}	—	10	pF
Input Impedance, f = 1.0 kHz ($I_C = 1.0$ mA, $V_{CE} = 5.0$ V) ($I_C = 5.0$ mA, $V_{CE} = 5.0$ V)	h_{ie}	 — —	 6000 2000	 ohms ohms
Small-Signal Current Gain, f = 1.0 kHz ($I_C = 1.0$ mA, $V_{CE} = 5.0$ V) ($I_C = 5.0$ mA, $V_{CE} = 5.0$ V)	h_{fe}	 40 50	 200 250	—
Magnitude of Forward Circuit Transfer Ratio, Common-Emitter ($I_C = 10$ mA, $V_{CE} = 15$ V)	$\|h_{fe}\|$	3.0	—	—
Output Admittance, f = 1.0 kHz ($I_C = 1.0$ mA, $V_{CE} = 5.0$ V) ($I_C = 5.0$ mA, $V_{CE} = 5.0$ V)	h_{oe}	 — —	 75 125	 μmho μmho
Collector Base Time Constant ($I_C = 10$ mA, $V_{CB} = 10$ V, f = 40 MHz)	$rb'C_c$	—	300	ps

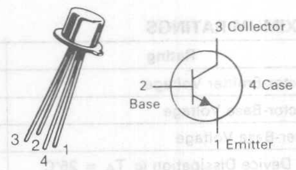
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 1.0%.

2N918

JAN, JTX, JTXV AVAILABLE

CASE 20-03, STYLE 10

TO-72 (TO-206AF)



AMPLIFIER TRANSISTOR

NPN SILICON

4

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	50	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	200 1.14	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	300 1.71	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

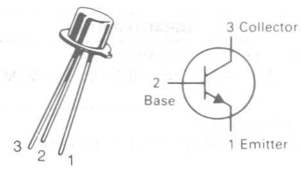
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage ($I_C = 3.0$ mAdc, $I_B = 0$)	$V_{CEO(sus)}$	15	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 1.0$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	30	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_E = 0$) ($V_{CB} = 15$ Vdc, $I_E = 0$, $T_A = 150°C$)	I_{CBO}	— —	.010 1.0	μAdc μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 3.0$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	20	—	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	0.4	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product(1) ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	600	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 140 kHz) ($V_{CB} = 0$, $I_E = 0$, f = 140 kHz)	C_{obo}	— —	1.7 3.0	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 140 kHz)	C_{ibo}	—	2.0	pF
Noise Figure ($I_C = 1.0$ mAdc, $V_{CE} = 6.0$ Vdc, $R_G = 400$ Ohms, f = 60 MHz)	NF	—	6.0	dB
FUNCTIONAL TEST				
Amplifier Power Gain ($V_{CB} = 12$ Vdc, $I_C = 6.0$ mAdc, f = 200 MHz)	G_{pe}	15	—	dB
Power Output ($V_{CB} = 15$ Vdc, $I_C = 8.0$ mAdc, f = 500 MHz)	P_o	30	—	mW
Collector Efficiency ($V_{CB} = 15$ Vdc, $I_C = 8.0$ mAdc, f = 500 MHz)	η	25	—	%

(1) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

2N930,A

JAN, JTX AVAILABLE
CASE 22-03, STYLE 1
TO-18 (TO-206AA)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N2481 for graphs.

MAXIMUM RATINGS

Rating	Symbol	2N930	2N930A	Unit
Collector-Emitter Voltage	V_{CEO}	45	60	Vdc
Collector-Base Voltage	V_{CBO}	45	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	6.0	Vdc
Collector Current	I_C	30		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.5 3.33		W mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.8 12		Watt mW/°C
Operating and Storage Temperature Temperature Range	T_J, T_{stg}	−65 to +175		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

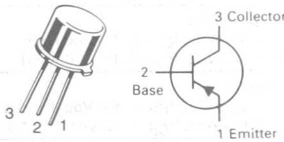
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (1) ($I_C = 10$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	45	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)		$V_{(BR)CBO}$	80	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	2N930 2N930A	$V_{(BR)EBO}$	5.0 6.0	— —	Vdc
Collector Cutoff Current ($V_{CE} = 5.0$ Vdc, $I_B = 0$)		I_{CEO}	—	2.0	nAdc
Collector Cutoff Current ($V_{CB} = 45$ Vdc, $I_E = 0$)	2N930 2N930A	I_{CBO}	— —	10 2.0	nAdc
Collector Cutoff Current ($V_{CE} = 45$ Vdc, $V_{BE} = 0$)	2N930 2N930A	I_{CES}	— —	10 2.0	nAdc
($V_{CE} = 45$ Vdc, $V_{BE} = 0$, $T_A = 170°C$)	2N930 2N930A		— —	10 2.0	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$)	2N930 2N930A	I_{EBO}	— —	10 2.0	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 1.0\ \mu$Adc, $V_{CE} = 5.0$ Vdc)	2N930A	h_{FE}	60	—	—
($I_C = 10\ \mu$Adc, $V_{CE} = 5.0$ Vdc)			100	300	
($I_C = 10\ \mu$Adc, $V_{CE} = 5.0$ Vdc, $T_A = -55°C$)	2N930 2N930A		20 30	— —	
($I_C = 500\ \mu$Adc, $V_{CE} = 5.0$ Vdc)	2N930 2N930A		150 —	— —	
($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc) (1)	2N930 2N930A		— —	600 600	

Characteristic		Symbol	Min	Max	Unit
(I_C = 10 mAdc, I_B = 0.5 mAdc)	2N930 2N930A		— —	1.0 0.5	
Base-Emitter Saturation Voltage (1) (I_C = 10 mAdc, I_B = 0.5 mAdc)		$V_{BE(sat)}$	0.7	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 500 μAdc, V_{CE} = 5.0 Vdc, f = 30 MHz)	2N930 2N930A	f_T	30 45	— —	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	2N930 2N930A	C_{obo}	— —	8.0 6.0	pF
Input Impedance (I_E = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)		h_{ib}	25	32	ohms
Voltage Feedback Ratio (I_E = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)		h_{rb}	—	600	X 10^{-6}
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)		h_{fe}	150	600	—
Output Admittance (I_E = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)		h_{ob}	—	1.0	μmhos
Noise Figure (I_C = 10 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 k ohms, f = 10 Hz to 15.7 kHz)		NF	—	3.0	dB

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

Collector-Emitter Voltage ($R_{BE} \leq 10$ Ohms)	V_{CER}	⟵ 50 ⟶	Vdc
Collector-Base Voltage	V_{CBO}	50	60	Vdc
Emitter-Base Voltage	V_{EBO}	⟵ 5.0 ⟶	Vdc
Collector Current — Continuous	I_C	⟵ 600 ⟶	mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	⟵ 600 ⟶ ⟵ 3.43 ⟶	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	⟵ 2.0 ⟶ ⟵ 11.43 ⟶	Watts mW/°C
Total Device Dissipation @ $T_C = 100°C$ 2N1132A	P_D	⟵ 1.0 ⟶	Watts
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

JAN AVAILABLE
CASE 79-02, STYLE 1
TO-39 (TO-205AD)



SWITCHING TRANSISTOR

PNP SILICON

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	87.49	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	291.55	°C/W

Refer to 2N2904 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

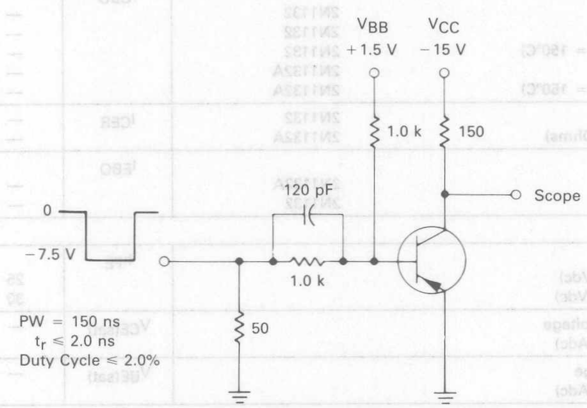
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 10$ mA)	2N1132A 2N1132	$V_{(BR)CEO}$	40 35	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	 2N1132 2N1132A	$V_{(BR)CBO}$	 50 60	 — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$) ($I_E = 1.0$ mA, $I_C = 0$)	 2N1132 2N1132A	$V_{(BR)EBO}$	 5.0 5.0	— —	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$) ($V_{CB} = 50$ Vdc, $I_E = 0$) ($V_{CB} = 30$ Vdc, $I_E = 0$, $T_A = 150°C$) ($V_{CB} = 45$ Vdc, $I_E = 0$) ($V_{CB} = 45$ Vdc, $I_E = 0$, $T_A = 150°C$)	 2N1132 2N1132 2N1132 2N1132A 2N1132A	I_{CBO}	 — — — — —	 1.0 100 100 0.5 50	μAdc
Collector Cutoff Current ($V_{CE} = 50$ V, $R_{BE} = \leq 10$ Ohms)	2N1132 2N1132A	I_{CER}	— —	10 10	mA mA
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$) ($V_{BE} = 2.0$ Vdc, $I_C = 0$)	 2N1132A 2N1132	I_{EBO}	 — —	 100 100	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)		h_{FE}	 25 30	 — 90	—
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)		$V_{CE(sat)}$	—	1.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)		$V_{BE(sat)}$	—	1.3	Vdc

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)		f_T	60	—	MHz
Output Capacitance		C_{obo}			pF
(V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	2N1132,		—	45	
(V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	2N1132A		—	30	
Input Capacitance		C_{ibo}			pF
(V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 kHz)	2N1132,		—	80	
(V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	2N1132A		—	80	
Input Impedance		h_{ib}			Ohms
(I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz			25	35	
(I_C = 5.0 mAdc, V_{CB} = 10 Vdc, f = 1.0 kHz			—	10	
Voltage Feedback Ratio		h_{rb}			X 10^{-4}
(I_C = 5.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)			—	8.0	
(I_C = 5.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)				8.0	
Small-Signal Current Gain		h_{fe}			—
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	2N1132,		25	100	
	2N1132A		25	75	
(I_C = 5.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N1132,		30	—	
	2N1132A		30		
Output Admittance		h_{ob}			µmhos
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)			—	1.0	
(I_C = 5.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)			—	5.0	
SWITCHING CHARACTERISTICS					
Turn-On Time	2N1132A	t_{on}	—	45	ns
Turn-Off Time	2N1132A	t_{off}	—	35	ns

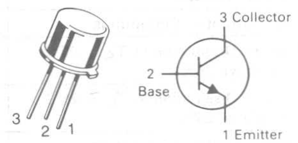
(1) Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.

FIGURE 1 SWITCHING TIMES TEST CIRCUIT



2N1613

JAN, JTX, JTXV AVAILABLE
CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N3019 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage ($R_{BE} \leq 10$ Ohms)	V_{CER}	50	Vdc
Collector-Base Voltage	V_{CBO}	75	Vdc
Emitter-Base Voltage	V_{EBO}	7.0	Vdc
Collector Current — Continuous	I_C	500	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.8 4.57	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	3.0 17.15	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	58.3	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

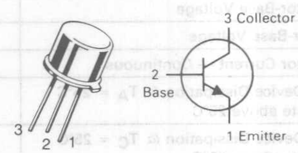
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 100$ mAdc, $R_{BE} \leq 10$ Ohms)	$V_{CER(sus)}$	50	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	75	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	7.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 60$ Vdc, $I_E = 0$) ($V_{CB} = 60$ Vdc, $I_E = 0$, $T_A = 150°C$)	I_{CBO}	— —	— —	10 10	nAdc μAdc
Emitter Cutoff Current ($V_{EB} = 5.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	10	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 100$ μAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, $T_A = -55°C$) ($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 500$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	20 35 20 40 20	35 50 — 80 30	— — — 120 —	—
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{CE(sat)}$	—	0.3	1.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{BE(sat)}$	—	0.78	1.3	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(1) ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)	f_T	60	—	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	10	25	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz)	C_{ibo}	—	50	80	pF
Input Impedance ($I_C = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CB} = 10$ Vdc, f = 1.0 kHz)	h_{ib}	24 4.0	— —	34 8.0	Ohms
Voltage Feedback Ratio ($I_C = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CB} = 10$ Vdc, f = 1.0 kHz)	h_{rb}	— —	— —	3.0 3.0	$\times 10^{-4}$
Small-Signal Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	30 35	— —	100 150	—
Output Admittance ($I_C = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CB} = 10$ Vdc, f = 1.0 kHz)	h_{ob}	0.05 0.05	— —	0.5 0.5	μmhos
Noise Figure ($I_C = 0.3$ mAdc, $V_{CE} = 10$ Vdc, $R_S = 510$ Ohms, f = 1.0 kHz, Bandwidth = 1.0 Hz)	NF	—	—	12	dB
SWITCHING CHARACTERISTICS					
Switching Time	$t_d + t_r + t_f$	—	—	30	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2N1711 For Specifications, See 2N718A Data.

2N1893

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	80	Vdc
Collector-Emitter Voltage	V_{CER}	100	Vdc
Collector-Base Voltage	V_{CBO}	120	Vdc
Emitter-Base Voltage	V_{EBO}	7.0	Vdc
Collector Current — Continuous	I_C	0.5	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.8 4.57	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	3.0 17.2	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	58.3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	219	°C/W

Refer to 2N3019 for graphs.

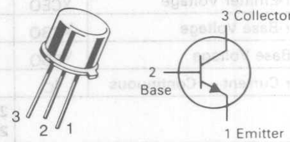
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 100$ mAdc, $R_{BE} = 10$ ohms)	$V_{CER(sus)}$	100	—	Vdc
Collector-Emitter Sustaining Voltage(1) ($I_C = 30$ mAdc, $I_B = 0$)	$V_{CEO(sus)}$	80	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	120	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	7.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 90$ Vdc, $I_E = 0$) ($V_{CB} = 90$ Vdc, $I_E = 0$, $T_A = 150°C$)	I_{CBO}	— —	0.01 15	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$)	I_{EBO}	—	0.01	μAdc
ON CHARACTERISTICS				
DC Current Gain(1) ($I_C = 0.1$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, $T_A = -55°C$) ($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	20 35 20 40	— — — 120	—
Collector-Emitter Saturation Voltage ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc) ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{CE(sat)}$	— —	1.2 5.0	Vdc
Base-Emitter Saturation Voltage ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc) ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{BE(sat)}$	— —	0.9 1.3	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)	f_T	50	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, 100 kHz ≤ f ≤ 1.0 MHz)	C_{obo}		15	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, 100 kHz ≤ f ≤ 1.0 MHz)	C_{ibo}		85	pF
Input Impedance ($I_C = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CB} = 10$ Vdc, f = 1.0 kHz)	h_{ib}	20 4.0	30 8.0	Ohms
Voltage Feedback Ratio ($I_C = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CB} = 10$ Vdc, f = 1.0 kHz)	h_{rb}	— —	1.25 1.5	$X\ 10^{-4}$
Small-Signal Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	30 45	100 —	—
Output Admittance ($I_C = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CB} = 10$ Vdc, f = 1.0 kHz)	h_{ob}	— —	0.5 0.5	μmho

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2N2102

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N3019 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	65	Vdc
Collector-Emitter Voltage, $R_{BE} \leq 10$ Ohms	V_{CER}	80	Vdc
Collector-Base Voltage	V_{CBO}	120	Vdc
Emitter-Base Voltage	V_{EBO}	7.0	Vdc
Collector Current — Continuous	I_C	1.0	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 5.71	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5.0 28.6	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	175	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 100$ mAdc, $R_{BE} \leq 10$ ohms)	$V_{CER(sus)}$	80	—	—	Vdc
Collector-Emitter Sustaining Voltage(2) ($I_C = 100$ mAdc, $I_B = 0$)	$V_{CEO(sus)}$	65	—	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 100\ \mu$Adc, $V_{EB} = 1.5$ Vdc)	$V_{(BR)CEX}$	120	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	120	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	7.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 60$ Vdc, $I_E = 0$) ($V_{CB} = 60$ Vdc, $I_E = 0$, $T_A = 150°C$)	I_{CBO}	— —	— —	2.0 2.0	nAdc μAdc
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	2.0	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, $T_A = -55°C$) ($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)(2) ($I_C = 500$ mAdc, $V_{CE} = 10$ Vdc)(2) ($I_C = 1.0$ Adc, $V_{CE} = 10$ Vdc)(2)	h_{FE}	20 35 20 40 25 10	— — — — — —	— — — 120 — —	—
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{CE(sat)}$	—	0.15	0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{BE(sat)}$	—	0.88	1.1	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)	f_T	60	—	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	6.0	15	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz)	C_{ibo}	—	50	80	pF
Input Impedance ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{ib}	24 4.0	— —	34 8.0	Ohms
Voltage Feedback Ratio ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{rb}	— —	— —	3.0 3.0	X 10^{-4}
Small-Signal Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	30 35	— —	100 150	—
Output Admittance ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz) ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{ob}	0.01 0.01	— —	0.5 1.0	μmho
Noise Figure ($I_C = 300\ \mu$Adc, $V_{CE} = 10$ Vdc, $R_S = 1.0$ k Ohm, f = 1.0 kHz, Bandwidth = 1.0 Hz)	NF	—	4.0	6.0	dB
SWITCHING CHARACTERISTICS					
Switching Time	$t_d + t_r + t_f$	—	—	30	ns

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board. (2) Pulse Test: Pulse Width $\leq 300\ \mu s$, Duty Cycle $\leq 2.0\%$.

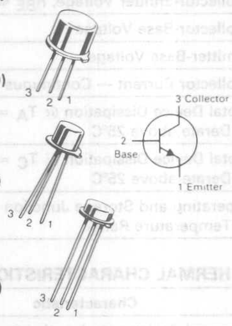
2N2218,A/2N2219,A
2N2221,A/2N2222,A
2N5581/82

JAN, JTX, JTXV AVAILABLE

2N2218,A
2N2219,A
CASE 79-02
TO-39 (TO-205AD)
STYLE 1

2N2221,A
2N2222,A
CASE 22-03
TO-18 (TO-206AA)
STYLE 1

2N5581
2N5582
CASE 26-03
TO-46 (TO-206AB)
STYLE 1



GENERAL PURPOSE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	2N2218 2N2219 2N2221 2N2222	2N2218A 2N2219A 2N2221A 2N2222A	2N5581 2N5582	Unit
Collector-Emitter Voltage	V_{CEO}	30	40	40	Vdc
Collector-Base Voltage	V_{CBO}	60	75	75	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	6.0	6.0	Vdc
Collector Current — Continuous	I_C	800	800	800	mAdc
		2N2218,A 2N2219,A	2N2221,A 2N2222,A	2N5581 2N5582	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.8 4.57	0.5 2.28	0.6 3.33	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	3.0 17.1	1.2 6.85	2.0 11.43	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−65 to +200		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 10$ mAdc, $I_B = 0$)	Non-A Suffix A-Suffix, 2N5581, 2N5582	$V_{(BR)CEO}$	30 40		Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	Non-A Suffix A-Suffix, 2N5581, 2N5582	$V_{(BR)CBO}$	60 75	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	Non-A Suffix A-Suffix, 2N5581, 2N5582	$V_{(BR)EBO}$	5.0 6.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 60$ Vdc, $V_{EB(off)} = 3.0$ Vdc)	A-Suffix, 2N5581, 2N5582	I_{CEX}	—	10	nAdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$) ($V_{CB} = 60$ Vdc, $I_E = 0$) ($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = 150°C$) ($V_{CB} = 60$ Vdc, $I_E = 0$, $T_A = 150°C$)	Non-A Suffix A-Suffix, 2N5581, 2N5582 Non-A Suffix A-Suffix, 2N5581, 2N5582	I_{CBO}	— — — —	0.01 0.01 10 10	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)	A-Suffix, 2N5581, 2N5582	I_{EBO}	—	10	nAdc
Base Cutoff Current ($V_{CE} = 60$ Vdc, $V_{EB(off)} = 3.0$ Vdc)	A-Suffix	I_{BL}	—	20	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 10$ Vdc)	2N2218,A, 2N2221,A, 2N5581(1) 2N2219,A, 2N2222,A, 2N5582(1)	h_{FE}	20 35	— —	
($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc)	2N2218,A, 2N2221,A, 2N5581 2N2219,A, 2N2222,A, 2N5582		25 50	— —	
($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc)	2N2218,A, 2N2221,A, 2N5581(1) 2N2219,A, 2N2222,A, 2N5582(1)		35 75	— —	
($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, $T_A = -55°C$)	2N2218A, 2N2221A, 2N5581 2N2219A, 2N2222A, 2N5582		15 35	— —	
($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)(1)	2N2218,A, 2N2221,A, 2N5581 2N2219,A, 2N2222,A, 2N5582		40 100	120 300	

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
(I_C = 150 mAdc, V_{CE} = 1.0 Vdc)(1)	2N2218,A, 2N2221,A, 2N5581		20	—	
	2N2219,A, 2N2222,A, 2N5582		50	—	
(I_C = 500 mAdc, V_{CE} = 10 Vdc)(1)	2N2218, 2N2221		20	—	
	2N2219, 2N2222		30	—	
	2N2218A, 2N2221A, 2N5581		25	—	
	2N2219A, 2N2222A, 2N5582		40	—	
Collector-Emitter Saturation Voltage(1)		$V_{CE(sat)}$			Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)	Non-A Suffix		—	0.4	
	A-Suffix, 2N5581, 2N5582		—	0.3	
(I_C = 500 mAdc, I_B = 50 mAdc)	Non-A Suffix		—	1.6	
	A-Suffix, 2N5581, 2N5582		—	1.0	
Base-Emitter Saturation Voltage(1)		$V_{BE(sat)}$			Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)	Non-A Suffix		0.6	1.3	
	A-Suffix, 2N5581, 2N5582		0.6	1.2	
(I_C = 500 mAdc, I_B = 50 mAdc)	Non-A Suffix		—	2.6	
	A-Suffix, 2N5581, 2N5582		—	2.0	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2)		f_T			MHz
(I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	All Types, Except		250	—	
	2N2219A, 2N2222A, 2N5582		300	—	
Output Capacitance(3) (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	8.0	pF
Input Capacitance(3)		C_{ibo}			pF
(V_{EB} = 0.5 Vdc, I_C = 0, f = 100 kHz)	Non-A Suffix		—	30	
	A-Suffix, 2N5581, 2N5582		—	25	
Input Impedance		h_{ie}			kohms
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N2218A, 2N2221A		1.0	3.5	
	2N2219A, 2N2222A		2.0	8.0	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N2218A, 2N2221A		0.2	1.0	
	2N2219A, 2N2222A		0.25	1.25	
Voltage Feedback Ratio		h_{re}			X 10^{-4}
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N2218A, 2N2221A		—	5.0	
	2N2219A, 2N2222A		—	8.0	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N2218A, 2N2221A		—	2.5	
	2N2219A, 2N2222A		—	4.0	
Small-Signal Current Gain		h_{fe}			—
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N2218A, 2N2221A		30	150	
	2N2219A, 2N2222A		50	300	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N2218A, 2N2221A		50	300	
	2N2219A, 2N2222A		75	375	
Output Admittance		h_{oe}			μmhos
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N2218A, 2N2221A		3.0	15	
	2N2219A, 2N2222A		5.0	35	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N2218A, 2N2221A		10	100	
	2N2219A, 2N2222A		25	200	
Collector Base Time Constant (I_E = 20 mAdc, V_{CB} = 20 Vdc, f = 31.8 MHz)	A-Suffix	$r_{b'}C_c$	—	150	ps
Noise Figure (I_C = 100 μAdc, V_{CE} = 10 Vdc, R_S = 1.0 kohm, f = 1.0 kHz)	2N2222A	NF	—	4.0	dB
Real Part of Common-Emitter High Frequency Input Impedance		$Re(h_{ie})$	—	60	Ohms
(I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 300 MHz)	2N2218A, 2N2219A				
	2N2221A, 2N2222A				

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.
(3) 2N5581 and 2N5582 are Listed C_{cb} and C_{eb} for these conditions and values.

4

Characteristic		Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 30 Vdc, $V_{BE(off)}$ = 0.5 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc) (Figure 14)	t_d	—	10	ns
Rise Time		t_r	—	25	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc) (Figure15)	t_s	—	225	ns
Fall Time		t_f	—	60	ns
Active Region Time Constant (I_C = 150 mAdc, V_{CE} = 30 Vdc) (See Figure 12 for 2N2218A, 2N2219A, 2N2221A, 2N2222A)		T_A	—	2.5	ns

FIGURE 1 – NORMALIZED DC CURRENT GAIN

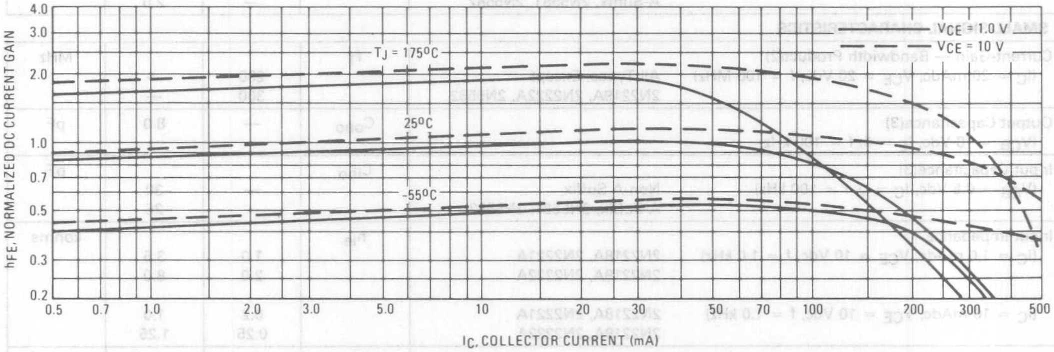
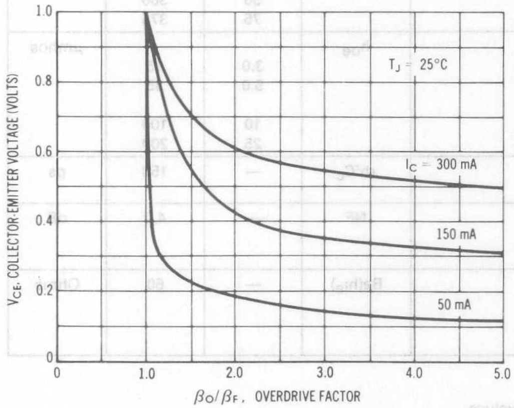


FIGURE 2 – COLLECTOR CHARACTERISTICS IN SATURATION REGION

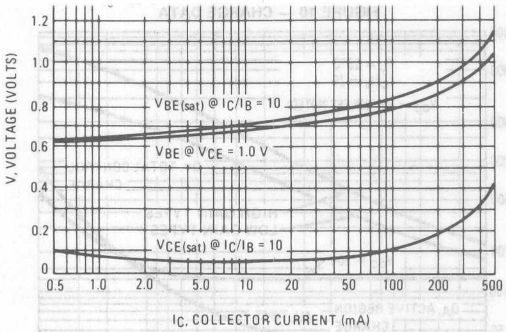


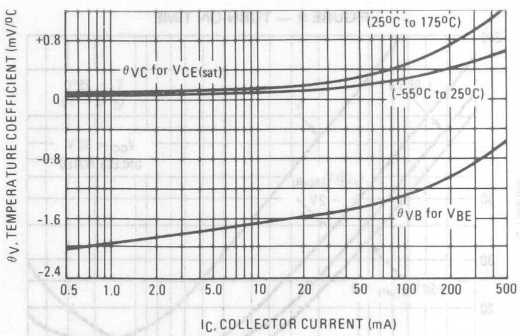
This graph shows the effect of base current on collector current. β_o (current gain at the edge of saturation) is the current gain of the transistor at 1 volt, and β_F (forced gain) is the ratio of I_C/I_B in a circuit.

EXAMPLE: For type 2N2219, estimate a base current (I_B) to insure saturation at a temperature of 25°C and a collector current of 150 mA.

Observe that at I_C = 150 mA an overdrive factor of at least 2.5 is required to drive the transistor well into the saturation region. From Figure 1, it is seen that h_{FE} @ 1 volt is approximately 0.62 of h_{FE} @ 10 volts. Using the guaranteed minimum gain of 100 @ 150 mA and 10 V, β_o = 62 and substituting values in the overdrive equation, we find:

$$\frac{\beta_o}{\beta_F} = \frac{h_{FE} \ @\ 1.0\,V}{I_C/I_B} \qquad 2.5 = \frac{62}{150/I_B} \qquad I_B \approx 6.0\ \text{mA}$$





h PARAMETERS

V_{CE} = 10 Vdc, f = 1.0 kHz, T_A = 25°C

This group of graphs illustrates the relationship between h_{fe} and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were selected and the same units were used to develop the correspondingly numbered curves on each graph.

FIGURE 5 — INPUT IMPEDANCE

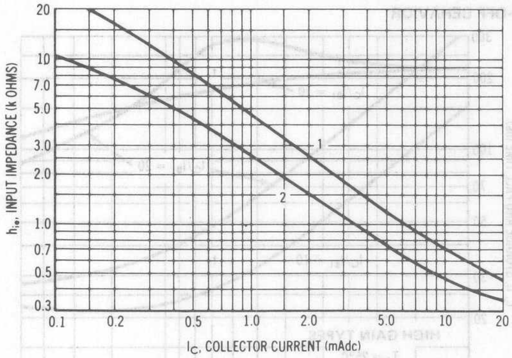


FIGURE 6 — VOLTAGE FEEDBACK RATIO

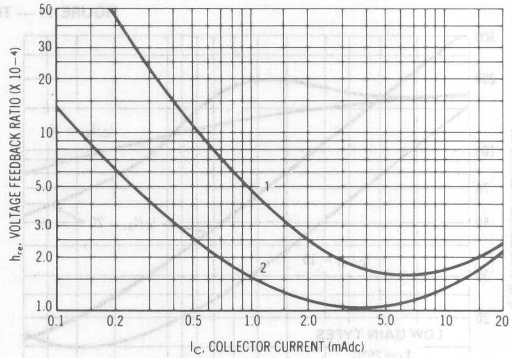


FIGURE 7 — CURRENT GAIN

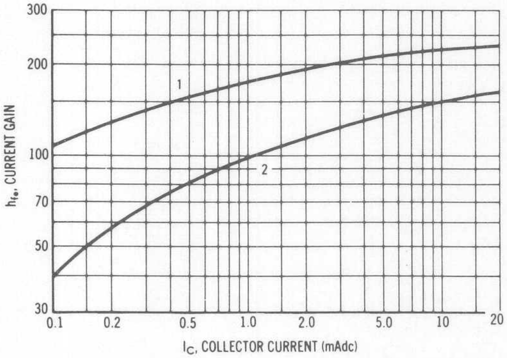
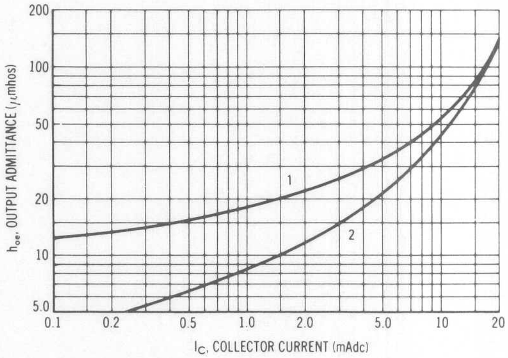


FIGURE 8 — OUTPUT ADMITTANCE



4

SWITCHING TIME CHARACTERISTICS

FIGURE 9 — TURN-ON TIME

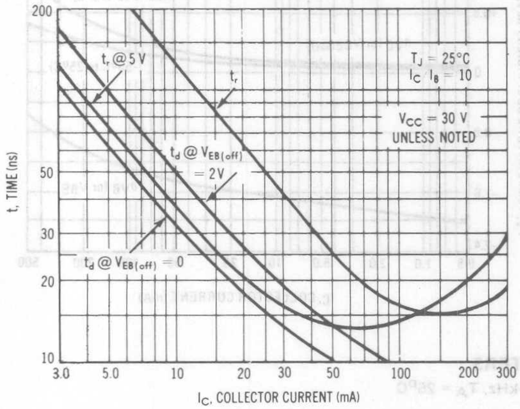


FIGURE 10 — CHARGE DATA

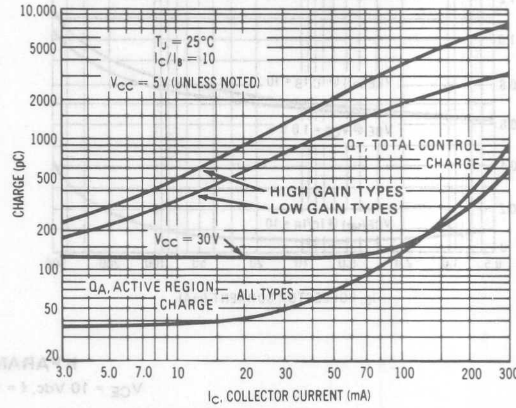


FIGURE 11 — TURN-OFF BEHAVIOR

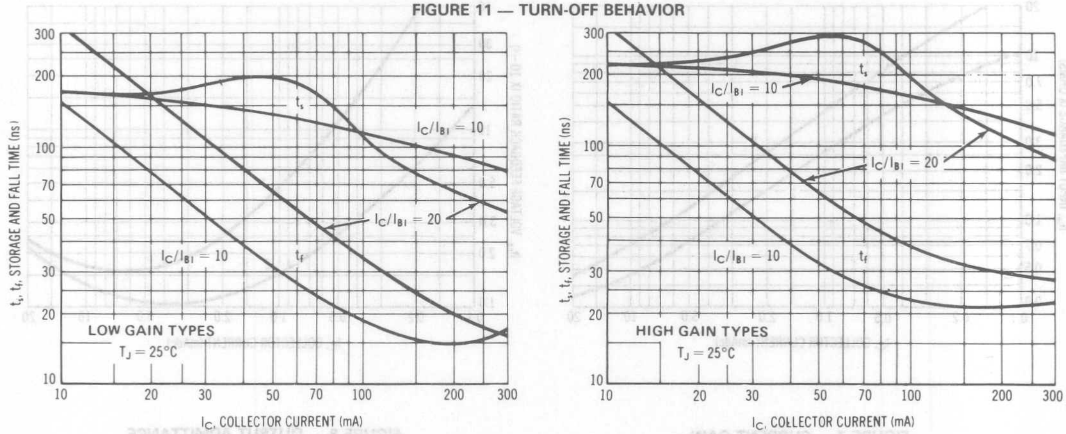


FIGURE 12 — DELAY AND RISE TIME EQUIVALENT TEST CIRCUIT

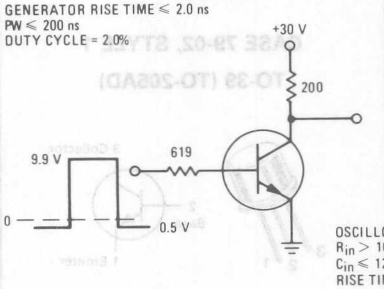
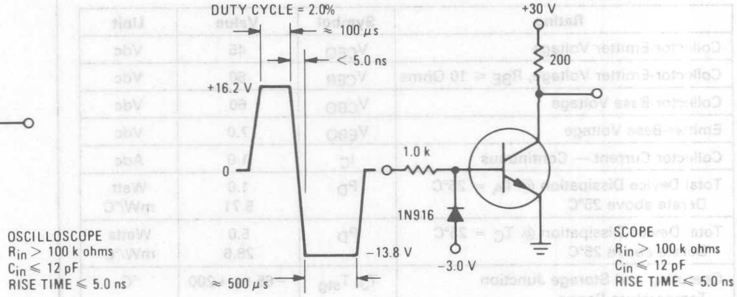


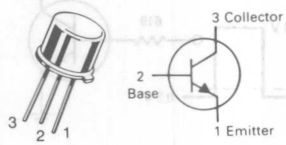
FIGURE 13 — STORAGE TIME AND FALL TIME EQUIVALENT TEST CIRCUIT



4

2N2270

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N3019 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	45	Vdc
Collector-Emitter Voltage, $R_{BE} \leq 10$ Ohms	V_{CER}	60	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	7.0	Vdc
Collector Current — Continuous	I_C	1.0	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 5.71	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5.0 28.6	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	175	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 100$ mAdc, $R_{BE} \leq 10$ Ohms)	$V_{(BR)CER}$	60	—	—	Vdc
Collector-Emitter Sustaining Voltage(2) ($I_C = 100$ mAdc, $I_B = 0$)	$V_{CEO(sus)}$	45	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.05\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 0.1$ mAdc, $I_C = 0$)	$V_{(BR)EBO}$	7.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 60$ Vdc, $I_E = 0$, $T_C = 25°C$) ($V_{CB} = 60$ Vdc, $I_E = 0$, $T_C = 150°C$)	I_{CBO}	— —	— —	0.05 100	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	 30 50	 90 135	 — 200	—
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{CE(sat)}$	—	0.15	0.9	Vdc
Base-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{BE(sat)}$	—	0.88	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)	f_T	100	250	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	10	15	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz)	C_{ibo}	—	60	80	pF
Small-Signal Current Gain ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	50	—	275	—
Noise Figure ($I_C = 0.3$ mAdc, $V_{CE} = 10$ Vdc, $R_S = 1.0$ k Ohm, f = 1.0 kHz, B.W. = 1.0 Hz)	NF	—	7.0	10	dB
SWITCHING CHARACTERISTICS					
Total Switching Time	$t_{on} + t_{off}$	—	—	30	ns

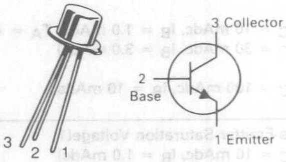
(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.
(2) Pulse Test: Pulse Width $\leq 300\ \mu s$, Duty Cycle $\leq 2.0\%$.

Collector-Emitter Voltage		V_{CES}	40	Vdc
Collector-Base Voltage		V_{CBO}	40	Vdc
Emitter-Base Voltage	2N2368,9,A 2N3227	V_{EBO}	4.5 6.0	Vdc
Collector Current (10 μs pulse)		$I_{C(Peak)}$	500	mA
Collector Current — Continuous	2N2369A, 2N3227	I_C	200	mA
Total Device Dissipation @ T_A = 25°C Derate above 25°C		P_D	0.36 2.06	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	2N3227	P_D	1.2 6.85	Watts mW/°C
Total Device Dissipation @ T_C = 100°C Derate above 100°C		P_D	.68 6.85	Watts mW/°C
Operating and Storage Junction Temperature Range		T_J, T_{stg}	−65 to +200	°C

2N3227

2N2369A JAN, JTX JTXV AVAILABLE

CASE 22-03, STYLE 1 TO-18 (TO-206AA)



SWITCHING TRANSISTOR

NPN SILICON

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, V_{BE} = 0)	2N3227	$V_{(BR)CEO}$	20	—	Vdc
Collector-Emitter Breakdown Voltage (I_C = 10 μA, V_{BE} = 0)		$V_{(BR)CES}$	40	—	Vdc
Collector-Emitter Sustaining Voltage(1) (I_C = 10 mAdc, I_B = 0)		$V_{CEO(sus)}$	15	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μA, I_B = 0)		$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_E = 0)	2N2368, 2N2369, 2N2369A 2N3227	$V_{(BR)EBO}$	4.5 6.0	— —	Vdc
Collector Cutoff Current (V_{CE} = 20 Vdc, V_{BE} = 3.0 Vdc)	2N3227	I_{CEX}	—	0.2	μAdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0)	2N2368, 2N2369 2N3227	I_{CBO}	— —	0.4 0.2	μAdc
(V_{CB} = 20 Vdc, I_E = 0, T_A = 150°C)	2N2368, 2N2369, 2N2369A 2N3227		— —	30 50	
Collector Cutoff Current (V_{CE} = 20 Vdc, V_{BE} = 0)	2N2369A	I_{CES}	—	0.4	μAdc
Base Current (V_{CE} = 20 Vdc, V_{BE} = 0)	2N2369A	I_B	—	0.4	μAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	2N2368 2N2369 2N2369A 2N3227	h_{FE}	20 40 — 100	60 120 120 300	—
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc, T_A = −55°C)	2N2368 2N2369 2N3227		10 20 40	— — —	
(I_C = 10 mAdc, V_{CE} = 0.35 Vdc, T_A = −55°C) (I_C = 30 mAdc, V_{CE} = 0.4 Vdc)	2N2369A 2N2369A		20 30	— —	

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
(I_C = 100 mAdc, V_{CE} = 1.0 Vdc)	2N2369A 2N3227		20 30	— —	
(I_C = 100 mAdc, V_{CE} = 2.0 Vdc)	2N2368 2N2369		10 20	— —	
Collector-Emitter Saturation Voltage(1)		$V_{CE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)	2N2368, 2N2369, 2N3227 2N2369A		— —	0.25 0.20	
(I_C = 10 mAdc, I_B = 1.0 mAdc, T_A = +125°C) (I_C = 30 mAdc, I_B = 3.0 mAdc)	2N2369A 2N2369A			0.30 0.25	
(I_C = 100 mAdc, I_B = 10 mAdc)	2N2369A 2N3227		— —	0.50 .45	
Base-Emitter Saturation Voltage(1)		$V_{BE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 10 mAdc, I_B = 1.0 mAdc, T_A = +125°C) (I_C = 10 mAdc, I_B = 1.0 mAdc, T_A = −55°C) (I_C = 30 mAdc, I_B = 3.0 mAdc)	All Types 2N2369A 2N2369A 2N2369A		0.70 0.59 —	0.85 — 1.02 1.15	
(I_C = 100 mAdc, I_B = 10 mAdc)	2N2369A 2N3227		— 0.8	1.60 1.4	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	 2N2368 2N2369, 2N2369A, 2N3227	f_T	 400 500	 — —	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 140 kHz)	All Types	C_{obo}	—	4.0	pF
Input Capacitance (V_{BE} = 1.0 Vdc, I_C = 0, f = 140 kHz)	2N3227	C_{ibo}	—	4.0	pF
SWITCHING CHARACTERISTICS					
Delay Time (V_{CC} = 10 V, V_{EB} = 2.0 Vdc, 100 mA, I_{B1} = 10 mA)	2N3227	t_d	—	5.0	ns
Rise Time (V_{CC} = 10 V, V_{EB} = 2.0 Vdc, 100 mA, I_{B1} = 10 mA)	2N3227	t_r	—	18	ns
Storage Time (I_C = I_{B1} = 10 mAdc, I_{B2} = −10 mAdc) (I_C = 100 mAdc, I_{B1} = I_{B2} = 10 mAdc, V_{CC} = 10 V)	 2N2368 2N2369A 2N3227	t_s	 — — —	 10 13 13	ns
Fall Time (V_{CC} = 10 V, I_C = 100 mA, I_{B1} = I_{B2} = 10 mA)	2N3227	t_f	—	15	ns
Turn-On Time (I_C = 10 mAdc, I_{B1} = 3.0 mA, I_{B2} = −1.5 mA, V_{CC} = 3.0 Vdc)	All Types	t_{on}	—	12	ns
Turn-Off Time (I_C = 10 mAdc, I_{B1} = 3.0 mA, I_{B2} = −1.5 mA, V_{CC} = 3.0 Vdc)	2N2368 2N2369, 2N2369A, 2N3227	t_{off}	— — — —	— — 15 18	ns
Total Control Charge (I_C = 10 mA, I_B = 1.0 mA, V_{CC} = 3.0 V)	2N3227	Q_T	—	50	pC

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS FOR 2N2369, 2N3227

FIGURE 1 — t_{on} CIRCUIT — 10 mA

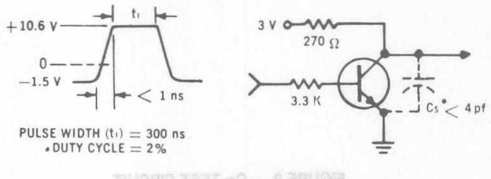


FIGURE 2 — t_{on} CIRCUIT — 100 mA

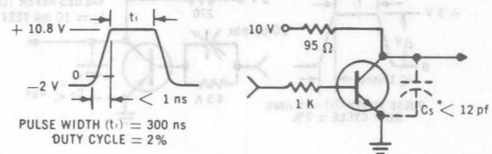


FIGURE 3 — t_{off} CIRCUIT — 10 mA

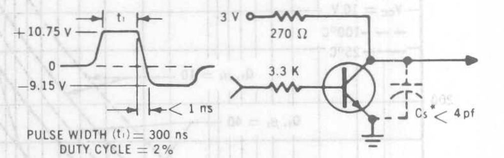
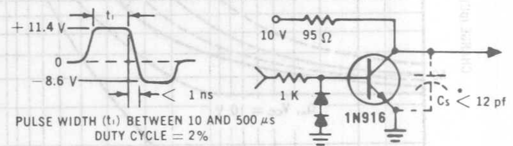


FIGURE 4 — t_{off} CIRCUIT — 100 mA



*Total shunt capacitance of test jig and connectors.

4

FIGURE 5 — TURN-ON AND TURN-OFF TIME TEST CIRCUIT

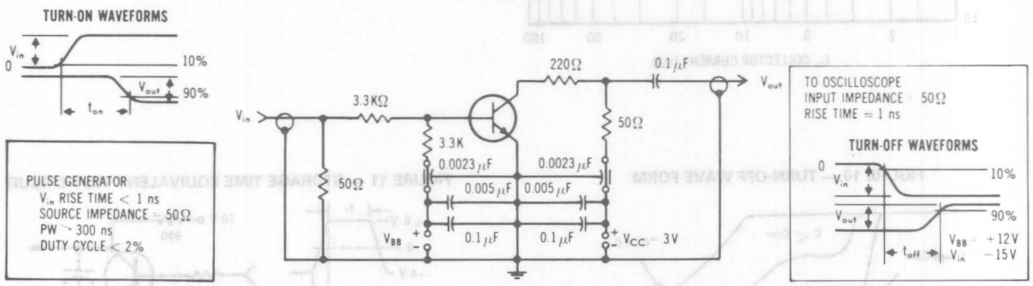


FIGURE 6 — JUNCTION CAPACITANCE VARIATIONS

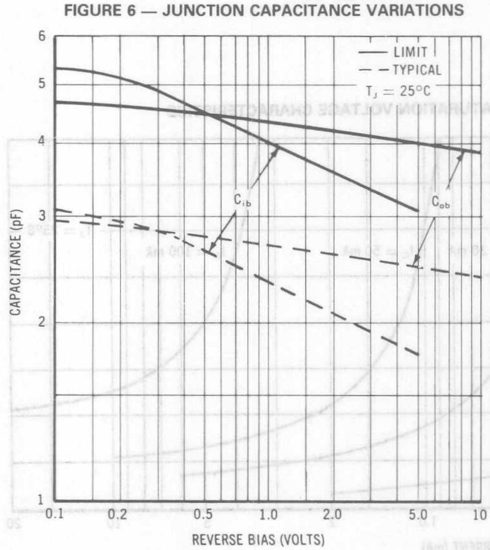


FIGURE 7 — TYPICAL SWITCHING TIMES

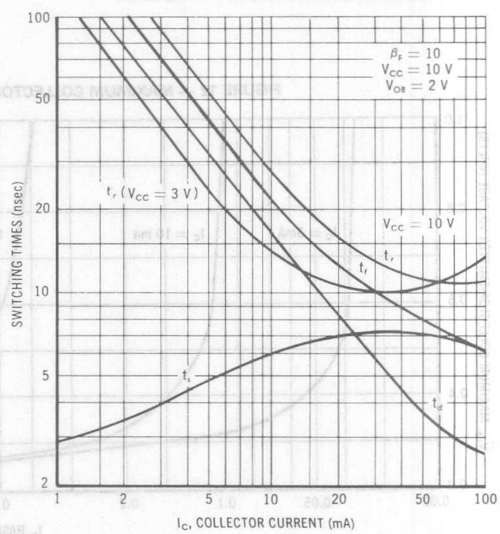


FIGURE 8 — MAXIMUM CHARGE DATA

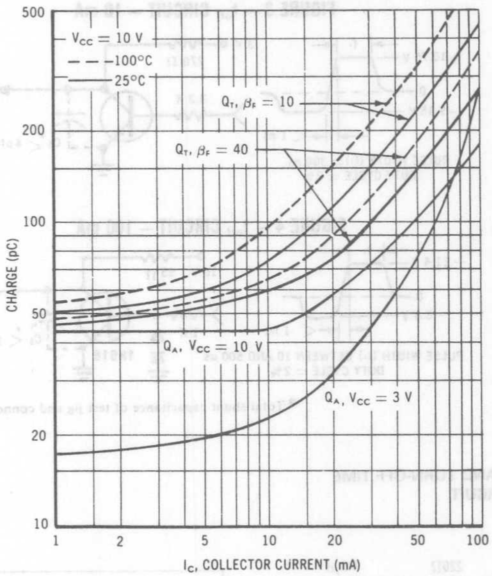


FIGURE 9 — Q_T TEST CIRCUIT

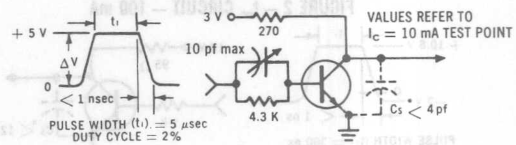


FIGURE 10 — TURN-OFF WAVE FORM

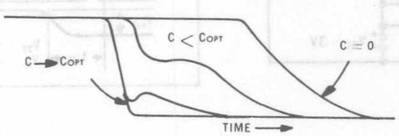


FIGURE 11 — STORAGE TIME EQUIVALENT TEST CIRCUIT

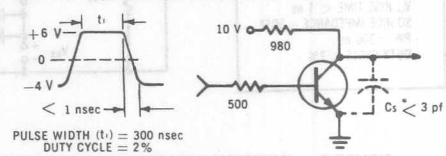


FIGURE 12 — MAXIMUM COLLECTOR SATURATION VOLTAGE CHARACTERISTICS

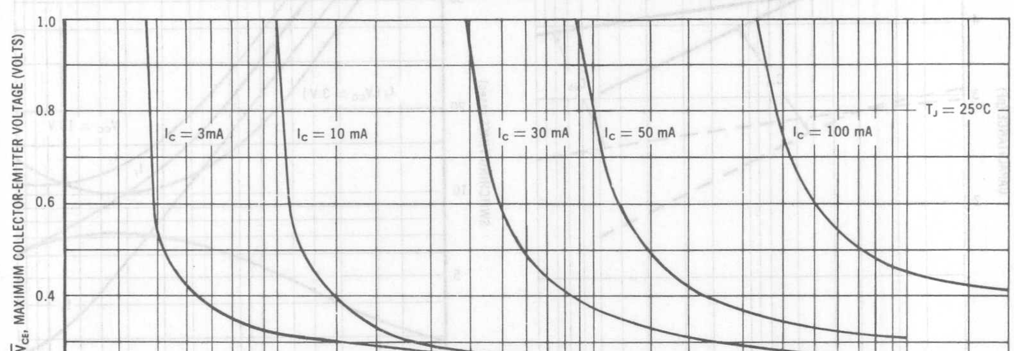


FIGURE 13 — MINIMUM CURRENT GAIN CHARACTERISTICS

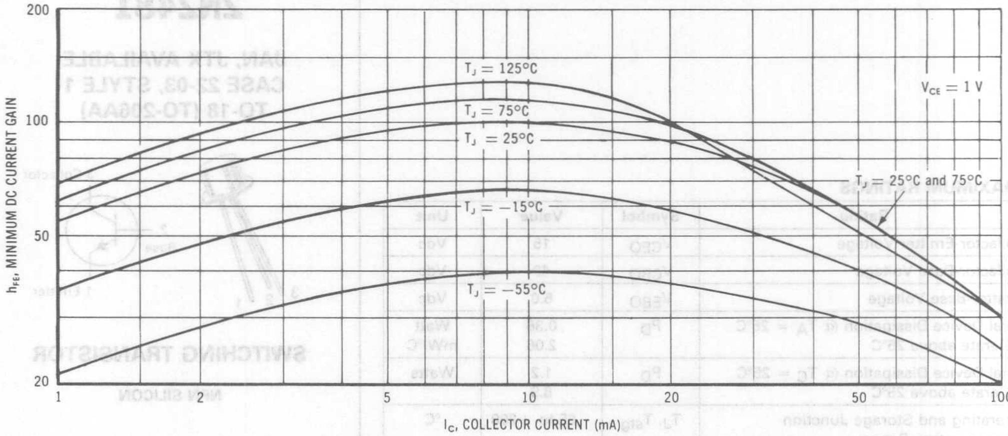


FIGURE 14 — SATURATION VOLTAGE LIMITS

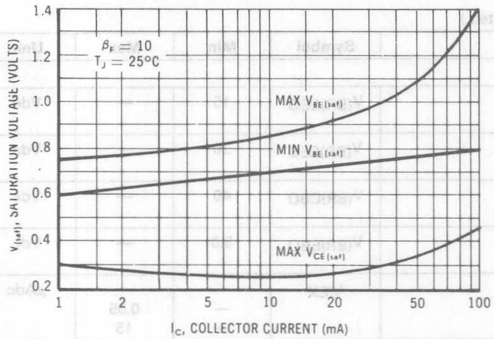
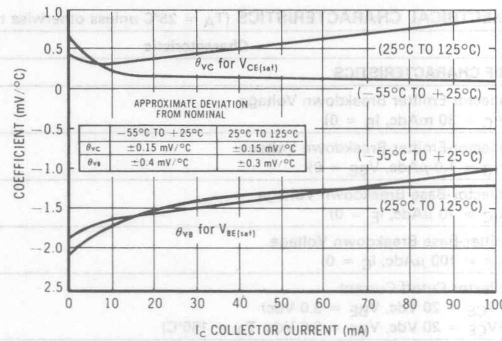
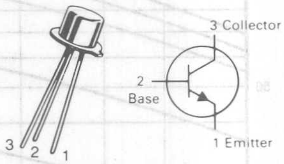


FIGURE 15 — TYPICAL TEMPERATURE COEFFICIENTS



JAN, JTX AVAILABLE
CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.36 2.06	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.2 6.9	Watts
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 30 mAdc, I_B = 0)	$V_{(BR)CEO}$	15	—	Vdc
Collector-Emitter Breakdown Voltage (I_C = 1.0 μAdc, V_{BE} = 0)	$V_{(BR)CES}$	30	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CE} = 20 Vdc, V_{BE} = 3.0 Vdc) (V_{CE} = 20 Vdc, V_{BE} = 3.0 Vdc, T_A = 150°C)	I_{CEX}	 — —	 0.05 15	μAdc
Emitter Cutoff Current (V_{EB} = 4.0 Vdc, I_C = 0)	I_{EBO}	—	100	nAdc
Base Cutoff Current (V_{CE} = 20 Vdc, V_{BE} = 3.0 Vdc)	I_{BL}	—	50	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc, T_A = −55°C)(1) (I_C = 150 mAdc, V_{CE} = 1.0 Vdc)(1)	h_{FE}	 25 40 20 20	 — 120 — —	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc)(1)	$V_{CE(sat)}$	 — —	 0.25 0.40	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc)(1)	$V_{BE(sat)}$	 0.7 —	 0.82 1.25	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance (V_{CB} = 5.0 V, I_C = 0, f = 1.0 MHz)	C_{obo}	—	5.0	pF
Input Capacitance (V_{EB} = 0.5 V, f = 1.0 MHz)	C_{ibo}	—	7.0	pF
Small-Signal Current Gain (V_{CE} = 10 V, I_C = 10 mA, f = 100 MHz)	h_{fe}	3.0	—	—
Real Part of Input Impedance (I_C = 10 mA, V_{CE} = 10 V, f = 250 MHz)	$Re(h_{ie})$	—	60	Ohms

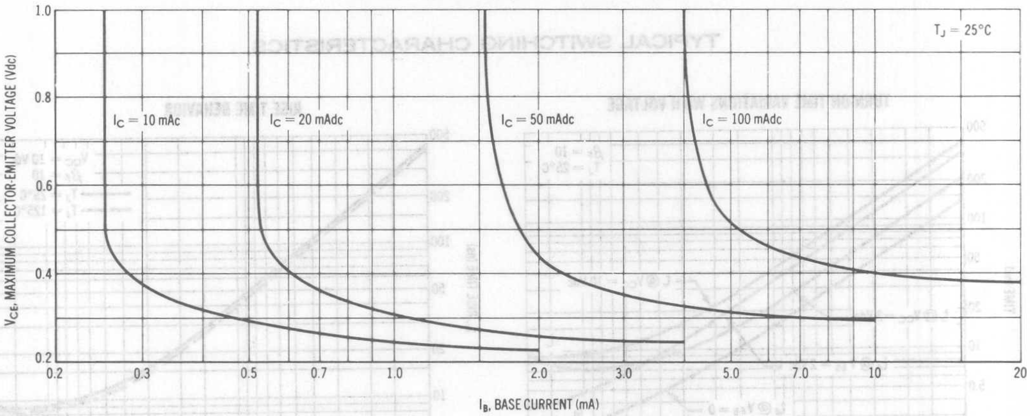
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS				
Storage Time (I_C = 10 mA, I_{B1} = 10 mA, I_{B2} = 10 mA)	t_s	—	20	ns
Turn-On Time	t_{on}			ns
(I_C = 100 mA, I_{B1} = 10 mA, $V_{BE(off)}$ = 2.0 V)		—	40	
(I_C = 10 mA, I_{B1} = 1.0 mA, $V_{BE(off)}$ = 2.0 V)		—	75	
Turn-Off Time	t_{off}			ns
(I_C = 100 mA, I_{B1} = 10 mA, I_{B2} = 5.0 mA)		—	55	
(I_C = 10 mA, I_{B1} = 1.0 mA, I_{B2} = 0.5 mA)		—	45	

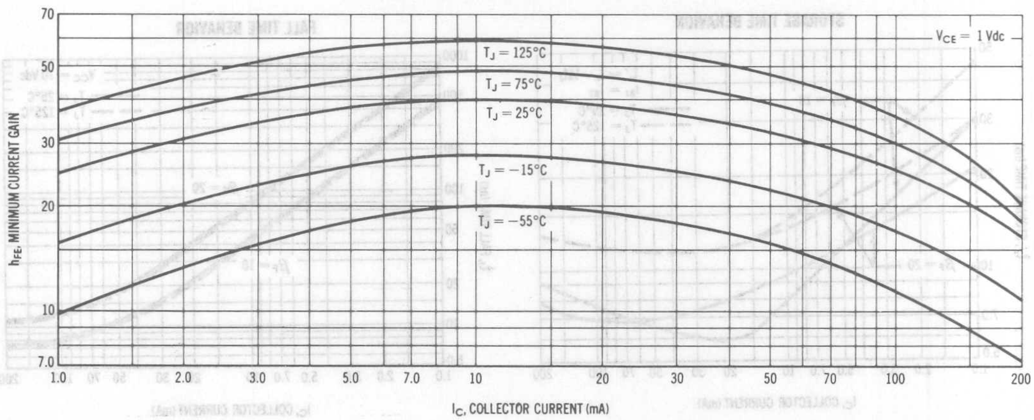
(1) Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

4

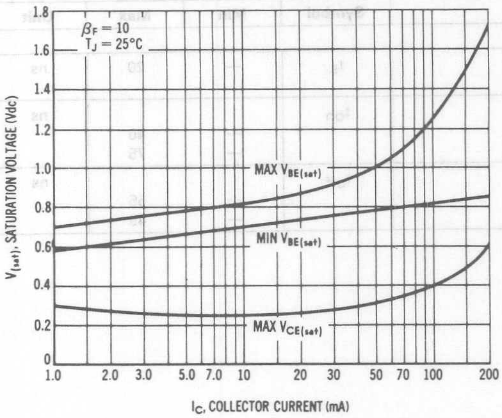
COLLECTOR SATURATION VOLTAGE CHARACTERISTICS



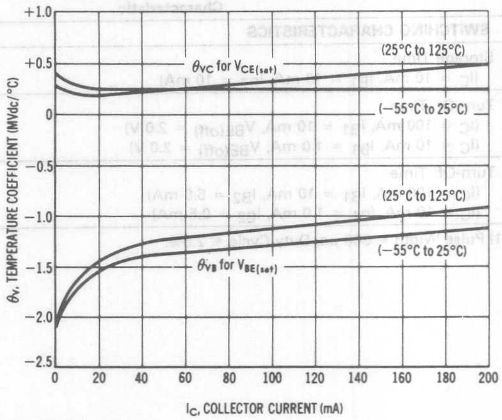
MINIMUM CURRENT GAIN CHARACTERISTICS



LIMITS OF SATURATION VOLTAGES

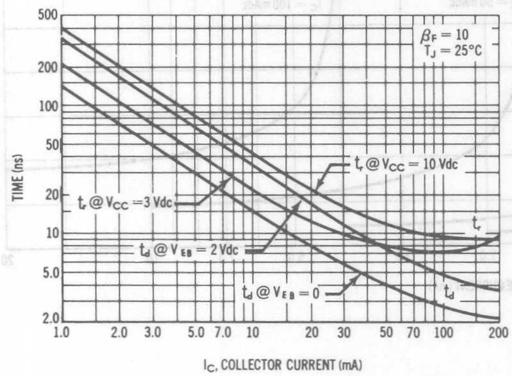


TYPICAL TEMPERATURE COEFFICIENTS

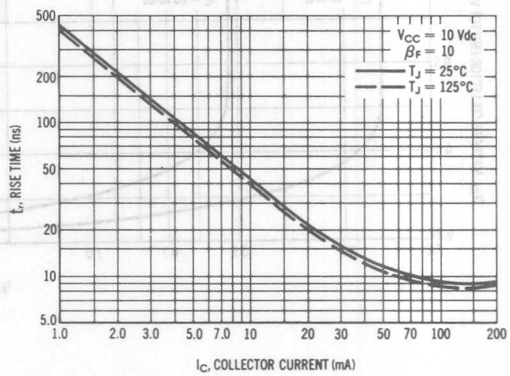


TYPICAL SWITCHING CHARACTERISTICS

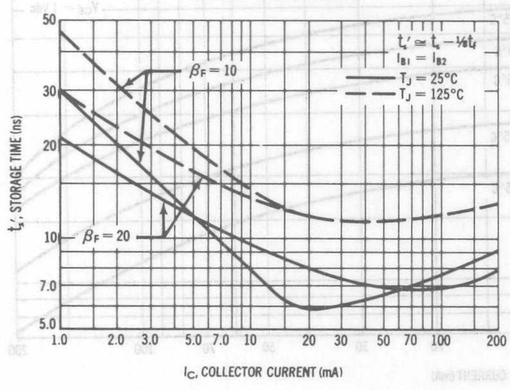
TURN-ON TIME VARIATIONS WITH VOLTAGE



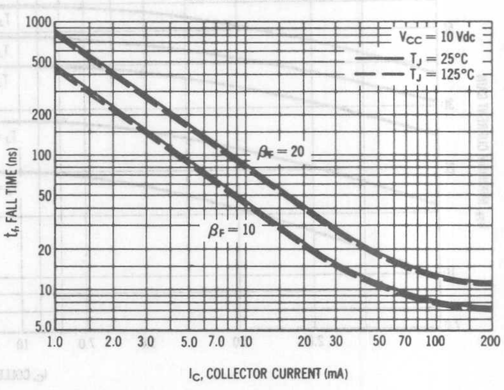
RISE TIME BEHAVIOR

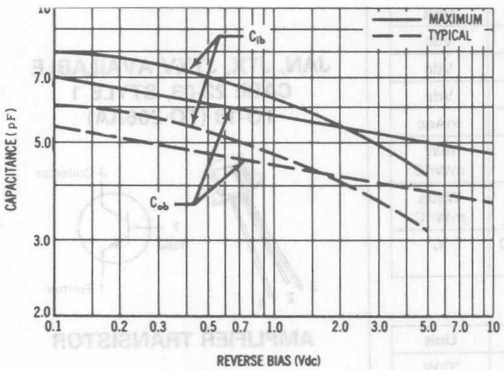


STORAGE TIME BEHAVIOR

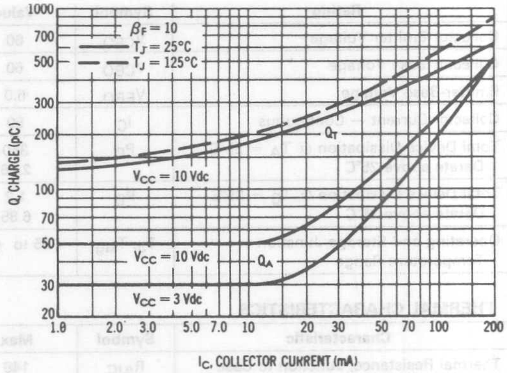


FALL TIME BEHAVIOR





MAXIMUM
TYPICAL
C_{ib}
C_{ob}
CAPACITANCE (pF)
REVERSE BIAS (Vdc)

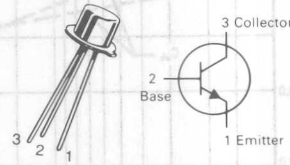


$\beta_F = 10$
$T_J = 25°C$
$T_J = 125°C$
Q_T
$V_{CC} = 10$ Vdc
$V_{CC} = 10$ Vdc
Q_A
$V_{CC} = 3$ Vdc
Q, CHARGE (pC)
I_C, COLLECTOR CURRENT (mA)

4

2N2484

JAN, JTX, JTXV AVAILABLE
CASE 22-03, STYLE 1
TO-18 (TO-206AA)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N2481 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	60	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	50	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	360 2.06	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.2 6.85	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	146	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	485	°C/W
Lead Temperature 1/16" from Case for 10 Seconds	T_L	300	°C

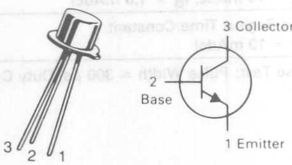
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	60	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	6.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 45$ Vdc, $I_E = 0$) ($V_{CB} = 45$ Vdc, $I_E = 0$, $T_A = 150°C$)	I_{CBO}	— —	— —	10 10	nAdc μAdc
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	10	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 1.0$ μAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 10$ μAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 10$ μAdc, $V_{CE} = 5.0$ Vdc, $T_A = 55°C$) ($I_C = 100$ μAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 500$ μAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc)(1)	h_{FE}	30 100 20 175 200 250 —	190 250 40 275 300 350 400	— 500 — — — — 800	—
Collector-Emitter Saturation Voltage ($I_C = 1.0$ mAdc, $I_B = 0.1$ mAdc)	$V_{CE(sat)}$	—	0.25	0.35	Vdc
Base-Emitter On Voltage ($I_C = 0.1$ mAdc, $V_{CE} = 5.0$ Vdc)	$V_{BE(on)}$	0.5	0.65	0.7	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 0.05$ mAdc, $V_{CE} = 5.0$ Vdc, f = 5.0 MHz) ($I_C = 0.5$ mAdc, $V_{CE} = 5.0$ Vdc, f = 30 MHz)	f_T	15 60	50 100	— —	MHz
Output Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 140 kHz)	C_{obo}	—	3.0	6.0	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 140 kHz)	C_{ibo}	—	4.0	6.0	pF
Input Impedance ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz)	h_{ie}	3.5	—	24	kΩ
Voltage Feedback Ratio ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz)	h_{re}	—	—	800	$X\ 10^{-6}$
Small-Signal Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz	h_{fe}	150	—	900	—
Output Admittance ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz)	h_{oe}	—	—	40	μmhos
Noise Figure ($I_C = 10$ μAdc, $V_{CE} = 5.0$ Vdc, $R_S = 10$ kΩ, f = 100 Hz, BW = 20 Hz) ($I_C = 10$ μAdc, $V_{CE} = 5.0$ Vdc, $R_S = 10$ kΩ, f = 1.0 kHz, BW = 200 Hz) ($I_C = 10$ μAdc, $V_{CE} = 5.0$ Vdc, $R_S = 10$ kΩ, f = 10 kHz, BW = 2.0 kHz) ($I_C = 10$ μAdc, $V_{CE} = 5.0$ Vdc, $R_S = 10$ kΩ, f = 10 Hz to 15.7 kHz, BW = 15.7 kHz)	NF	— — — —	8.0 — — —	10 3.0 2.0 3.0	dB

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.
(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2N2501

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

NPN SILICON

4

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	20	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.36 2.1	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.2 6.9	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

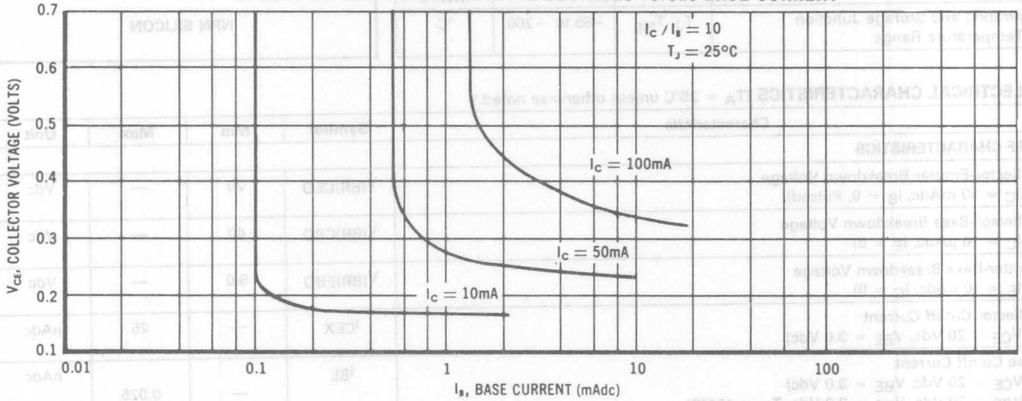
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 30 mAdc, I_B = 0, Pulsed)	$V_{(BR)CEO}$	20	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current (V_{CE} = 20 Vdc, V_{BE} = 3.0 Vdc)	I_{CEX}	—	25	nAdc
Base Cutoff Current (V_{CE} = 20 Vdc, V_{BE} = 3.0 Vdc) (V_{CE} = 20 Vdc, V_{BE} = 3.0 Vdc, T_A = 150°C)	I_{BL}	 — —	 0.025 50	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 100 μAdc, V_{CE} = 1.0 Vdc) (I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc, T_A = −55°C) (I_C = 50 mAdc, V_{CE} = 1.0 Vdc) (I_C = 100 mAdc, V_{CE} = 1.0 Vdc) (I_C = 500 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}	 20 30 50 20 40 30 10	 — — 150 — — — —	—
Collector-Emitter Saturation Voltage(1) (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc)	$V_{CE(sat)}$	 — — —	 0.2 0.3 0.4	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc)	$V_{BE(sat)}$	 — — —	 0.85 1.0 1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (V_{CE} = 20 Vdc, I_C = 10 mAdc, f = 100 MHz)	f_T	350	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	4.0	pF
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 100 kHz)	C_{ibo}	—	7.0	pF
Small-Signal Current Gain (V_{CE} = 20 Vdc, I_C = 10 mAdc, f = 100 MHz)	h_{fe}	3.5	—	—

Characteristic	Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS				
Charge Storage Time Constant ($I_C = I_{B1} = I_{B2} = 10$ mAdc)	τ_S	—	15	ns
Total Control Charge ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	Q_T	—	60	pC
Active Region Time Constant ($I_C = 10$ mAdc)	τ_A	—	2.5	ns

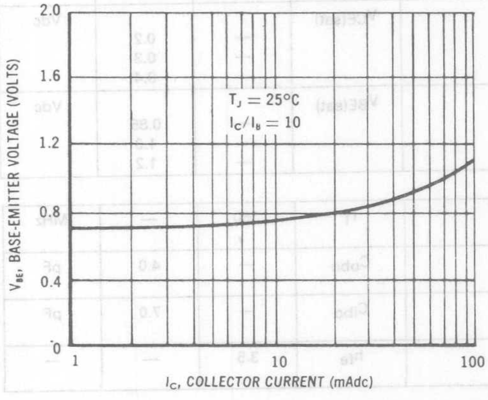
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

4

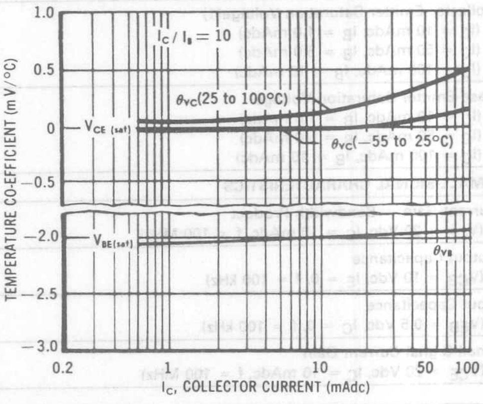
COLLECTOR-EMITTER SATURATION VOLTAGES versus BASE CURRENT



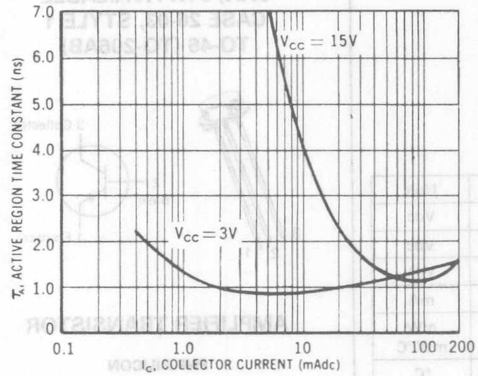
BASE-EMITTER VOLTAGE versus COLLECTOR CURRENT



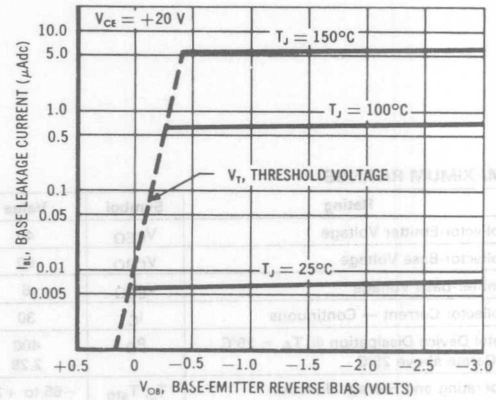
TEMPERATURE COEFFICIENTS



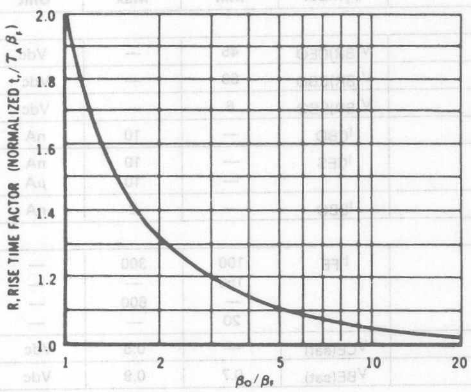
ACTIVE REGION TIME CONSTANT



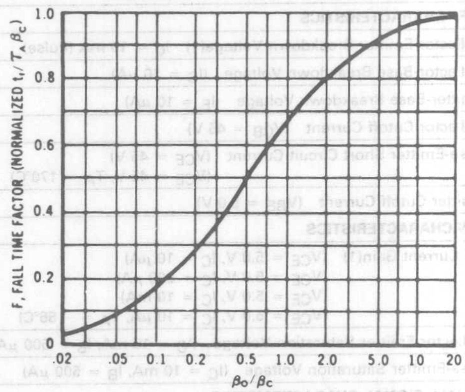
COMMON EMITTER DC
LEAKAGE CHARACTERISTICS



RISE TIME FACTOR

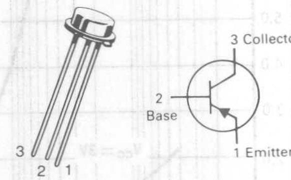


FALL TIME FACTOR



2N2605

JAN, JTX AVAILABLE
CASE 26-03, STYLE 1
TO-46 (TO-206AB)



AMPLIFIER TRANSISTOR

PNP SILICON

Refer to 2N3798 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	45	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6	Vdc
Collector Current — Continuous	I_C	30	mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	400 2.28	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

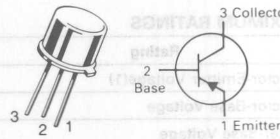
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) $I_C = 10$ mA (Pulse)	$V_{(BR)CEO}$	45	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu A$)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu A$)	$V_{(BR)EBO}$	6	—	Vdc
Collector Cutoff Current ($V_{CB} = 45$ V)	I_{CBO}	—	10	nA
Base-Emitter Short Circuit Current ($V_{CE} = 45$ V) ($V_{CE} = 45$ V, $T_A = 170°C$)	I_{CES}	— —	10 10	nA μA
Emitter Cutoff Current ($V_{BE} = 5.0$ V)	I_{EBO}	—	2	nA
ON CHARACTERISTICS				
DC Current Gain(1) ($V_{CE} = 5.0$ V, $I_C = 10\ \mu A$) ($V_{CE} = 5.0$ V, $I_C = 500\ \mu A$) ($V_{CE} = 5.0$ V, $I_C = 10$ mA) ($V_{CE} = 5.0$ V, $I_C = 10\ \mu A$, $T_A = -55°C$)	h_{FE}	100 150 — 20	300 — 600 —	— — — —
Collector-Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 500\ \mu A$)	$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 500\ \mu A$)	$V_{BE(sat)}$	0.7	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance ($V_{CB} = 5.0$ V, $I_E = 0$, f = 1.0 MHz)	C_{obo}	—	6	pF
Input Impedance ($V_{CE} = 5.0$ V, $I_C = 1.0$ mA, f = 100 MHz)	h_{ie}	—	200	Ω
Input Impedance ($V_{CB} = 5.0$ V, $I_E = 1.0$ mA, f = 1.0 kHz)	h_{ib}	25	35	Ω
Voltage Feedback Ratio ($V_{CB} = 5.0$ V, $I_E = 1.0$ mA, f = 1.0 kHz)	h_{rb}	—	10	10^{-4}
Small-Signal Current Gain ($V_{CB} = 5.0$ V, $I_E = 1.0$ mA, f = 1.0 kHz) ($V_{CB} = 5.0$ V, $I_C = 500\ \mu A$, f = 30 MHz)	h_{fe}	150 1.0	600 —	— —
Output Admittance ($V_{CB} = 5.0$ V, $I_E = 1.0$ mA, f = 1.0 kHz)	h_{ob}	—	1	μmho
Noise Figure(2) ($V_{CB} = 5.0$ V, $I_C = 10\ \mu A$, $R_g = 10$ k Ω, BW = 15.7 kHz)	NF	—	3	dB

(1) Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) Measured in amplifier with response down 3 dB at 10 Hz.

2N2800

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



SWITCHING TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	35	Vdc
Collector-Base Voltage	V_{CBO}	50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	800	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.8 4.57	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	3.0 17.14	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

Refer to 2N2904 for graphs.

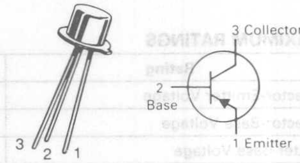
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 100$ mAdc, $I_B = 0$)	$V_{CEO(sus)}$	35	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	50	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 25$ Vdc, $V_{BE} = 0.5$ Vdc Off)	I_{CEX}	—	100	nAdc
Base Cutoff Current ($V_{CE} = 25$ Vdc, $V_{BE} = 0.5$ Vdc Off)	I_{BL}	—	100	nAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)(1) ($I_C = 150$ mAdc, $V_{CE} = 1.0$ Vdc)(1) ($I_C = 500$ mAdc, $V_{CE} = 10$ Vdc)(1)	h_{FE}	 20 30 15 25	 — 90 — —	—
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	$V_{CE(sat)}$	 — —	 0.4 1.2	Vdc
Base-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	$V_{BE(sat)}$	 — —	 1.3 1.8	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	120	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, f = 100 kHz)	C_{obo}	—	25	pF
SWITCHING CHARACTERISTICS				
Delay Time	t_d	9	25	ns
Rise Time	t_r	25	45	ns
Storage Time	t_s	100	225	ns
Fall Time	t_f	30	45	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2N2894

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

PNP SILICON

Refer to 2N869A for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage(1)	V_{CEO}	12	Vdc
Collector-Base Voltage	V_{CBO}	12	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	360 2.06	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1200 6.85	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

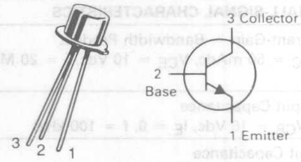
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 10\ \mu Adc$, $V_{BE} = 0$)	$V_{(BR)CES}$	12	—	Vdc
Collector-Emitter Sustaining Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{CEO(sus)}$	12	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu Adc$, $I_E = 0$)	$V_{(BR)CBO}$	12	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu Adc$, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 6.0$ Vdc, $I_E = 0$, $T_A = 125°C$)	I_{CBO}	—	10	μAdc
Collector Cutoff Current ($V_{CE} = 6.0$ Vdc, $V_{BE} = 0$)	I_{CES}	—	80	nAdc
Base Current ($V_{CE} = 6.0$ Vdc, $V_{BE} = 0$)	I_B	—	80	nAdc
ON CHARACTERISTICS				
DC Current Gain(2) ($I_C = 10$ mAdc, $V_{CE} = 0.3$ Vdc) ($I_C = 30$ mAdc, $V_{CE} = 0.5$ Vdc) ($I_C = 30$ mAdc, $V_{CE} = 0.5$ Vdc, $T_A = -55°C$) ($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc)(2)	h_{FE}	 30 40 17 25	 150 — —	—
Collector-Emitter Saturation Voltage(2) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 30$ mAdc, $I_B = 3.0$ mAdc) ($I_C = 100$ mAdc, $I_B = 10$ mAdc)	$V_{CE(sat)}$	 — — —	 0.15 0.2 0.5	Vdc
Base-Emitter Saturation Voltage(2) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 30$ mAdc, $I_B = 3.0$ mAdc) ($I_C = 100$ mAdc, $I_B = 10$ mAdc)	$V_{BE(sat)}$	 0.78 0.85 —	 0.98 1.2 1.7	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 30$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	400	—	MHz
Output Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 140 kHz)	C_{obo}	—	6.0	pF
Input Capacitance ($V_{BE} = -0.5$ Vdc, $I_C = 0$, f = 140 kHz)	C_{ibo}	—	6.0	pF
SWITCHING CHARACTERISTICS				
Turn-On Time ($V_{CC} = 2.0$ Vdc, $V_{BE} = 3.0$ Vdc, $I_C = 30$ mAdc, $I_{B1} = 1.5$ mAdc)	t_{on}	—	60	ns
Turn-Off Time ($V_{CC} = 2.0$ Vdc, $I_C = 30$ mAdc, $I_{B1} = I_{B2} = 1.5$ mAdc)	t_{off}	—	90	ns

(1) Applicable from 0.01 to 10 mAdc.
(2) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

2N2896
2N2897

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	2N2895	2N2896	2N2897	Unit
Collector-Emitter Voltage	V_{CEO}	65	90	45	Vdc
Collector-Emitter Voltage	V_{CER}	80	140	60	Vdc
Collector-Base Voltage	V_{CBO}	120	140	60	Vdc
Emitter-Base Voltage	V_{EBO}		7.0		Vdc
Collector Current — Continuous	I_C		1.0		Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D		0.5 2.86		Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D		1.8 10.3		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−65 to +200		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 100 mAdc, R_{BE} = 10 ohms)	2N2895 2N2896 2N2897	$V_{(BR)CES}$	80 140 60	— — —	Vdc
Collector-Emitter Sustaining Voltage(1) (I_C = 100 mAdc, I_B = 0)	2N2895 2N2896 2N2897	$V_{CEO(sus)}$	65 90 45	— — —	Vdc
Collector-Base Breakdown Voltage (I_C = 0.1 mAdc, I_E = 0)	2N2895 2N2896 2N2897	$V_{(BR)CBO}$	120 140 60	— — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 0.1 mAdc, I_C = 0)		$V_{(BR)EBO}$	7.0	—	Vdc
Collector Cutoff Current (V_{CB} = 60 Vdc, I_C = 0)	2N2895 2N2896 2N2897	I_{CBO}	— — —	0.002 0.01 0.05	μAdc
(V_{CB} = 60 Vdc, I_E = 0, T_A = +150°C)	2N2895 2N2897		— —	2.0 50	
(V_{CB} = 90 Vdc, I_E = 0) (V_{CB} = 90 Vdc, I_E = 0, T_A = +150°C)	2N2896 2N2896		— —	0.01 10	
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)	2N2895 2N2896 2N2897	I_{EBO}	— — —	0.005 0.01 0.05	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 10 μAdc, V_{CE} = 10 Vdc) (I_C = 100 μAdc, V_{CE} = 10 Vdc) (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc, T_A = −55°C)	 2N2895 2N2895 2N2896, 2N2897 2N2895 2N2895, 2N2896	h_{FE}	 10 20 35 35 20	 — — — — —	—
(I_C = 150 mAdc, V_{CE} = 10 Vdc)(1)	2N2895 2N2896 2N2897		40 60 50	120 200 200	
(I_C = 500 mAdc, V_{CE} = 10 Vdc)(1)	2N2895		25	—	

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

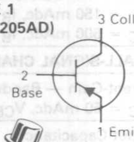
Characteristic		Symbol	Min	Max	Unit
Collector-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc)	2N2895, 2N2896 2N2897	$V_{CE(sat)}$	— —	0.6 1.0	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc)	2N2895, 2N2896 2N2897	$V_{BE(sat)}$	— —	1.2 1.3	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)	2N2895, 2N2896 2N2897	f_T	120 100	— 	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	15	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	80	pF
Small-Signal Current Gain (I_C = 5.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	2N2895 2N2896, 2N2897	h_{fe}	50 50	200 275	—
Noise Figure (I_C = 0.3 mAdc, V_{CE} = 10 Vdc, R_S = 500 ohms, f = 1.0 kHz, BW = 15 kHz)	2N2895	NF	—	8.0	dB

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 1.8%.

2N2904,A, 2N2905,A, 2N2906,A, 2N2907,A, 2N3485,A, 2N3486,A

JAN, JTX, JTXV AVAILABLE*

CASE 79-02, STYLE 1
2N2904/2905 TO-39 (TO-205AD)



CASE 22-03, STYLE 1
2N2906/2907 TO-18
(TO-206AA)

CASE 26-03, STYLE 1
2N3485/3486 TO-46 (TO-206AB)

GENERAL PURPOSE TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Non-A Suffix		A-Suffix	Unit
Collector-Emitter Voltage	V_{CEO}	40		60	Vdc
Collector-Base Voltage	V_{CBO}		60		Vdc
Emitter-Base Voltage	V_{EBO}		5.0		Vdc
Collector Current — Continuous	I_C		600		mAdc
		2N2904,A 2N2905,A	2N2906,A 2N2907,A	2N3485,A 2N3486,A	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	600 3.43	400 2.28	400 2.28	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	3.0 17.2	1.8 10.3	2.0 11.43	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−65 to +200		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

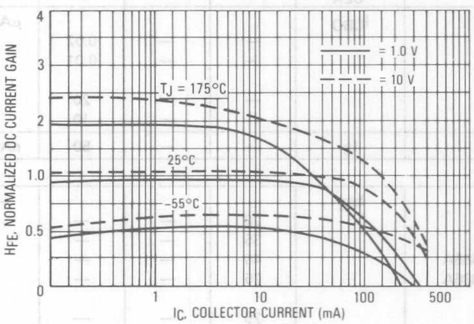
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(1)		$V_{(BR)CEO}$				Vdc
(I_C = 10 mAdc, I_B = 0)	Non-A Suffix		40	—	—	
	A-Suffix		60	—	—	
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CE} = 30 Vdc, V_{BE} = 0.5 Vdc)		I_{CEX}	—	—	50	nAdc
Collector Cutoff Current		I_{CBO}				μAdc
(V_{CB} = 50 Vdc, I_E = 0)	Non-A Suffix		—	—	0.02	
	A-Suffix		—	—	0.01	
(V_{CB} = 50 Vdc, I_E = 0, T_A = 150°C)	Non-A Suffix		—	—	20	
	A-Suffix		—	—	10	
Base Current (V_{CE} = 30 Vdc, V_{BE} = 0.5 Vdc)		I_B	—	—	50	nAdc
ON CHARACTERISTICS						
DC Current Gain		h_{FE}				—
(I_C = 0.1 mAdc, V_{CE} = 10 Vdc)	2N2904, 2N2906, 2N3485		20	—	—	
	2N2905, 2N2907, 2N3486		35	—	—	
	2N2904A, 2N2906A, 2N3485A		40	—	—	
	2N2905A, 2N2907A, 2N3486A		75	—	—	
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)	2N2904, 2N2906, 2N3485		25	—	—	
	2N2905, 2N2907, 2N3486		50	—	—	
	2N2904A, 2N2906A, 2N3485A		40	—	—	
	2N2905A, 2N2907A, 2N3486A		100	—	—	
(I_C = 10 mAdc, V_{CE} = 10 Vdc)	2N2904, 2N2906, 2N3485		35	—	—	
	2N2905, 2N2907, 2N3486		75	—	—	
	2N2904A, 2N2906A, 2N3485A		40	—	—	
	2N2905A, 2N2907A, 2N3486A		100	—	—	
(I_C = 150 mAdc, V_{CE} = 10 Vdc)(1)	2N2904A, 2N2906A, 2N3485A		40	—	120	
	2N2905A, 2N2907A, 2N3486A		100	—	300	
(I_C = 500 mAdc, V_{CE} = 10 Vdc)(1)	2N2904, 2N2906, 2N3485		20	—	—	
	2N2905, 2N2907, 2N3486		30	—	—	
	2N2904A, 2N2906A, 2N3485A		40	—	—	
	2N2905A, 2N2907A, 2N3486A		50	—	—	

***ALSO AVAILABLE 2N2905ALJANS AND 2N2907AJANS**

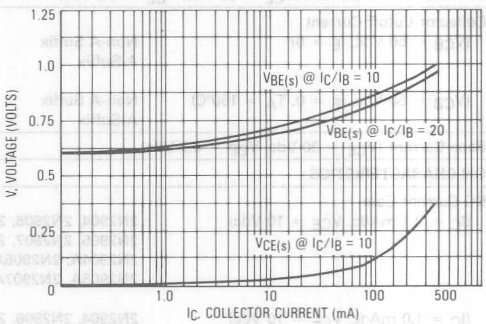
Characteristic	Symbol	Min	Typ	Max	Unit
Collector-Emitter Saturation Voltage(1)	$V_{CE(sat)}$				Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)		—	—	0.4	
(I_C = 500 mAdc, I_B = 50 mAdc)		—	—	1.6	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$				Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)(1)		—	—	1.3	
(I_C = 500 mAdc, I_B = 50 mAdc)		—	—	2.6	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 50 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	200	—	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	—	8.0	pF
Input Capacitance (V_{BE} = 2.0 Vdc, I_C = 0, f = 100 kHz)	C_{ibo}	—	—	30	pF
SWITCHING CHARACTERISTICS					
Turn-On Time	t_{on}	—	26	45	ns
Delay Time (V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_d	—	6.0	10	ns
Rise Time	t_r	—	20	40	ns
Turn-Off Time	t_{off}	—	70	100	ns
Storage Time (V_{CC} = 6.0 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_s	—	50	80	ns
Fall Time	t_f	—	20	30	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0.%
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

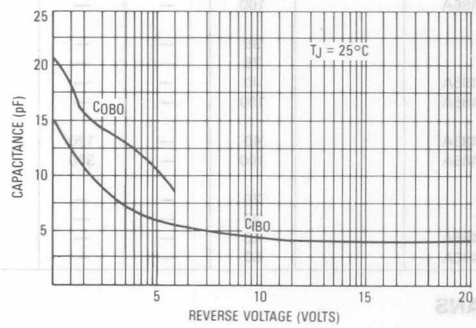
NORMALIZED DC CURRENT GAIN



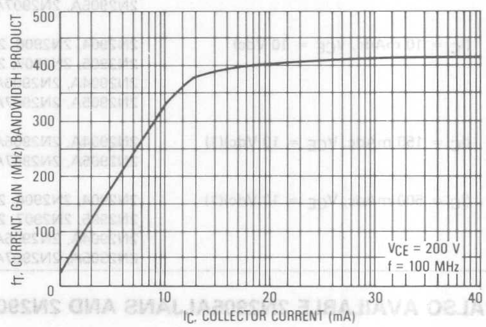
"ON" VOLTAGE

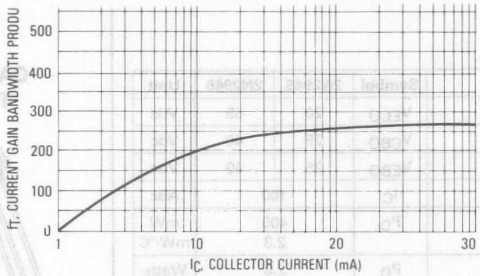


CAPACITANCE

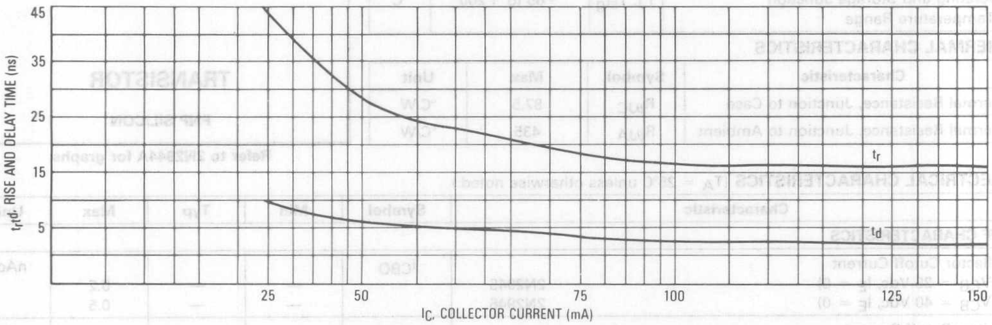


CURRENT GAIN—BANDWIDTH PRODUCT

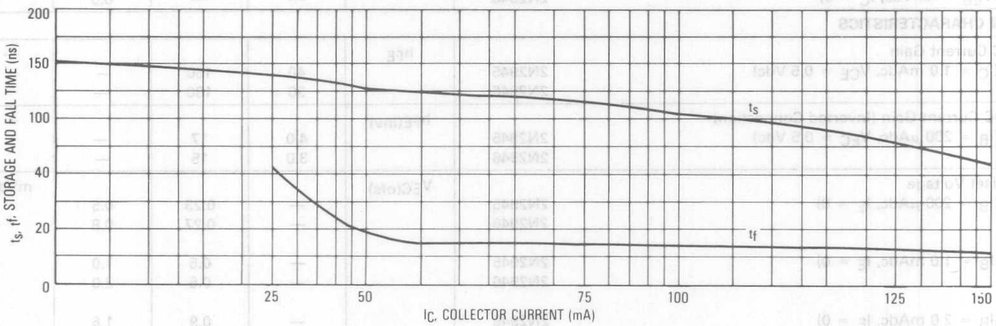




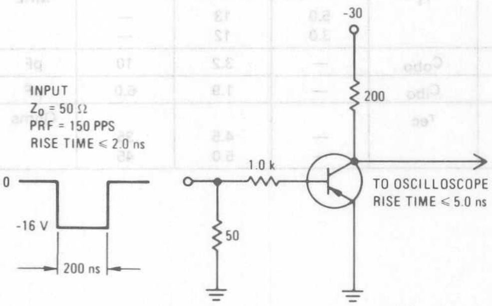
TURN ON BEHAVIOR



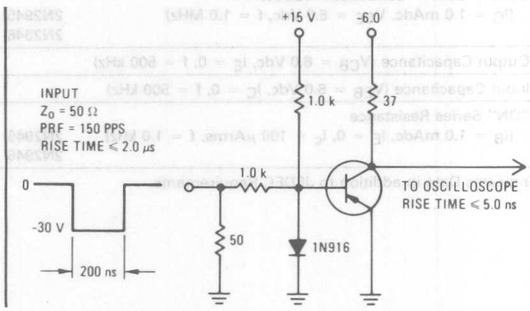
TURN OFF BEHAVIOR



DELAY AND RISE TIME TEST CIRCUIT



STORAGE AND FALL TIME TEST CIRCUIT

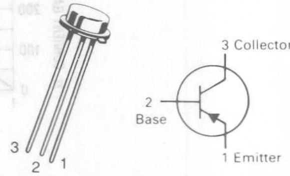


4

4

2N2945
2N2946

CASE 26-03, STYLE 1
TO-46 (TO-206AB)



TRANSISTOR

PNP SILICON

Refer to 2N2944A for graphs.

MAXIMUM RATINGS

Rating	Symbol	2N2945	2N2946	Unit
Emitter-Collector Voltage	V_{ECO}	20	35	Vdc
Collector-Base Voltage	V_{CBO}	25	40	Vdc
Emitter-Base Voltage	V_{EBO}	25	40	Vdc
Collector Current — Continuous	I_C	100		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	400 2.3		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.0 11.43		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	87.5	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	435	°C/W

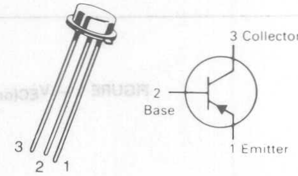
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector Cutoff Current		I_{CBO}				nAdc
($V_{CB} = 25$ Vdc, $I_E = 0$)	2N2945		—	—	0.2	
($V_{CB} = 40$ Vdc, $I_E = 0$)	2N2946		—	—	0.5	
Emitter Cutoff Current		I_{EBO}				nAdc
($V_{EB} = 25$ Vdc, $I_C = 0$)	2N2945		—	—	0.2	
($V_{EB} = 40$ Vdc, $I_C = 0$)	2N2946		—	—	0.5	
ON CHARACTERISTICS						
DC Current Gain		h_{FE}				—
($I_C = 1.0$ mAdc, $V_{CE} = 0.5$ Vdc)	2N2945		40	160	—	
	2N2946		30	130	—	
*DC Current Gain (Inverted Connection)		$h_{FE(inv)}$				—
($I_B = 200$ μAdc, $V_{EC} = 0.5$ Vdc)	2N2945		4.0	17	—	
	2N2946		3.0	15	—	
Offset Voltage		$V_{EC(ofs)}$				mVdc
($I_B = 200$ μAdc, $I_E = 0$)	2N2945		—	0.23	0.5	
	2N2946		—	0.27	0.8	
($I_B = 1.0$ mAdc, $I_E = 0$)	2N2945		—	0.5	1.0	
	2N2946		—	0.6	2.0	
($I_B = 2.0$ mAdc, $I_E = 0$)	2N2945		—	0.9	1.6	
	2N2946		—	1.0	2.5	
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product		f_T				MHz
($I_C = 1.0$ mAdc, $V_{CE} = 6.0$ Vdc, f = 1.0 MHz)	2N2945		5.0	13	—	
	2N2946		3.0	12	—	
Output Capacitance ($V_{CB} = 6.0$ Vdc, $I_E = 0$, f = 500 kHz)		C_{obo}	—	3.2	10	pF
Input Capacitance ($V_{EB} = 6.0$ Vdc, $I_C = 0$, f = 500 kHz)		C_{ibo}	—	1.9	6.0	pF
"ON" Series Resistance		r_{ec}				Ohms
($I_B = 1.0$ mAdc, $I_E = 0$, $I_c = 100$ μArms, f = 1.0 kHz)	2N2945		—	4.5	35	
	2N2946		—	5.0	45	

*Indicates Data in addition to JEDEC Requirements.

2N2945A
2N2946A

JAN, JTX, JTXV AVAILABLE
CASE 26-03, STYLE 1
TO-46 (TO-206AB)



CHOPPER TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	2N2945A	2N2946A	Unit
Emitter-Collector Voltage	V_{ECO}	20	35	Vdc
Collector-Base Voltage	V_{CBO}	25	40	Vdc
Emitter-Base Voltage	V_{EBO}	25	40	Vdc
Collector Current — Continuous	I_C	100		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	400 2.3		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.0 11.43		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C
Lead Temperature 1/16″ from Case for 10 seconds	T_L	240		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	435	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	87.5	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Emitter-Collector Breakdown Voltage		$V_{(BR)ECO}$				Vdc
($I_E = 10\ \mu Adc$, $I_B = 0$)	2N2945A		20	—	—	
	2N2946A		35	—	—	
Collector Cutoff Current		I_{CBO}				nAdc
($V_{CB} = 25$ Vdc, $I_E = 0$)	2N2945A		—	—	0.2	
($V_{CB} = 40$ Vdc, $I_E = 0$)	2N2946A		—	—	0.5	
($V_{CB} = 25$ Vdc, $I_E = 0$, $T_A = 100°C$)	2N2945A		—	—	20	
($V_{CB} = 40$ Vdc, $I_E = 0$, $T_A = 100°C$)	2N2946A		—	—	25	
Emitter Cutoff Current		I_{EBO}				nAdc
($V_{EB} = 25$ Vdc, $I_C = 0$)	2N2945A		—	—	0.2	
($V_{EB} = 40$ Vdc, $I_C = 0$)	2N2946A		—	—	0.5	
($V_{EB} = 25$ Vdc, $I_C = 0$, $T_A = 100°C$)	2N2945A		—	—	15	
($V_{EB} = 40$ Vdc, $I_C = 0$, $T_A = 100°C$)	2N2946A		—	—	20	
ON CHARACTERISTICS						
DC Current Gain		h_{FE}				—
($I_C = 1.0$ mAdc, $V_{CE} = 0.5$ Vdc)	2N2945A		70	200	—	
	2N2946A		50	200	—	
DC Current Gain (Inverted Connection)		$h_{FE(inv)}$				—
($I_B = 200\ \mu Adc$, $V_{EC} = 0.5$ Vdc)	2N2945A		30	32	—	
	2N2946A		20	25	—	
Offset Voltage		$V_{EC(ofs)}$				mVdc
($I_B = 200\ \mu Adc$, $I_E = 0$)	2N2945A		—	0.4	0.5	
	2N2946A		—	0.7	0.8	
($I_B = 1.0$ mAdc, $I_E = 0$)	2N2945A		—	0.5	1.0	
	2N2946A		—	0.6	2.0	
($I_B = 2.0$ mAdc, $I_E = 0$)	2N2945A		—	0.9	1.5	
	2N2946A		—	1.0	2.5	

4

Output Capacitance (V_{CB} = 6.0 Vdc, I_E = 0, f = 0.1 MHz to 1.0 MHz)		C_{obo}	—	3.2	10	pF
Input Capacitance (V_{EB} = 6.0 Vdc, I_C = 0, f = 0.1 MHz to 1.0 MHz)		C_{ibo}	—	1.9	6.0	pF
"ON" Series Resistance (I_B = 1.0 mAdc, I_E = 0, I_e = 100 μArms, f = 1.0 kHz)	2N2945A	$r_{ec(on)}$	—	5.0	6.0	Ohms
	2N2946A		—	7.0	8.0	

FIGURE 1 — $V_{EC(on)}$

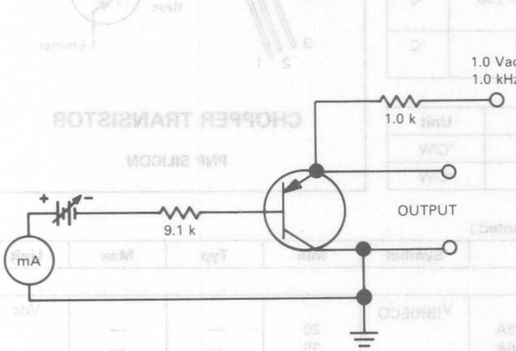
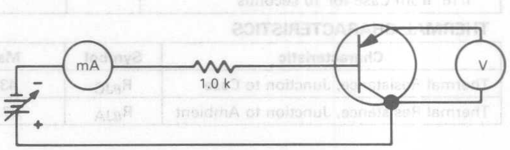


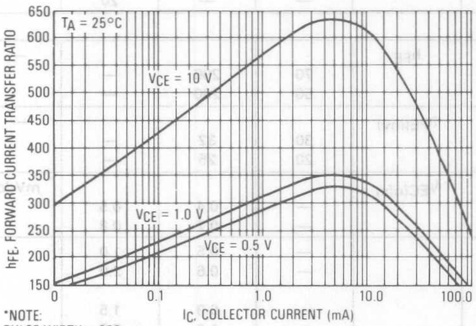
FIGURE 2 — $V_{EC(offset)}$



mA + + + + + - - - - - - 9.1 k 2% 1.0 Vac
10 k 2% Output Figure 1 — rec(on) rec(on) rec(on)
mA 1.0k 2% V

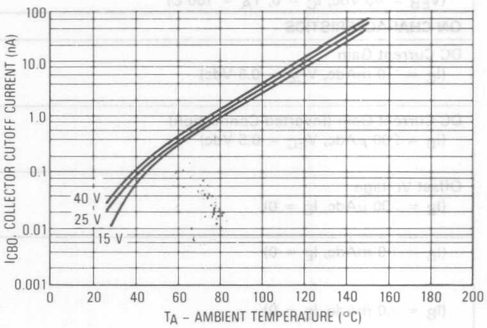
Output measured with H.P. 400D
Ac VTVM or equivalent.
1.0 mV = 1.0 Ω rec(on)

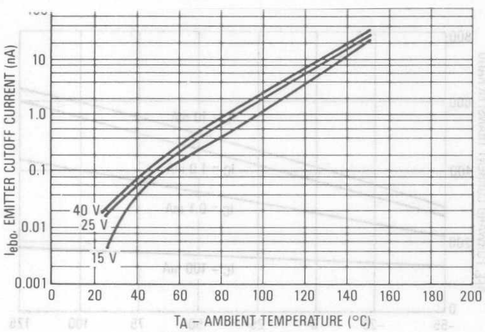
h_{FE} versus I_C

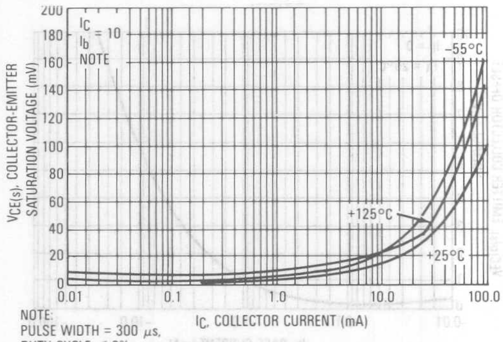


*NOTE:
PULSE WIDTH = 300 μs,
DUTY CYCLE ≤ 2%

I_{CBO} versus T_A

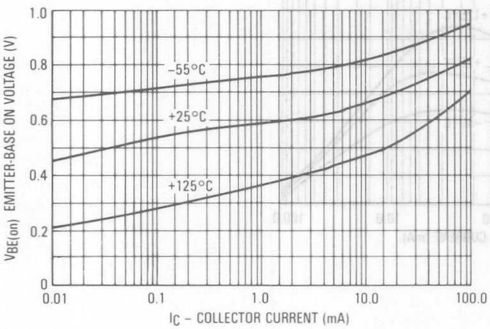




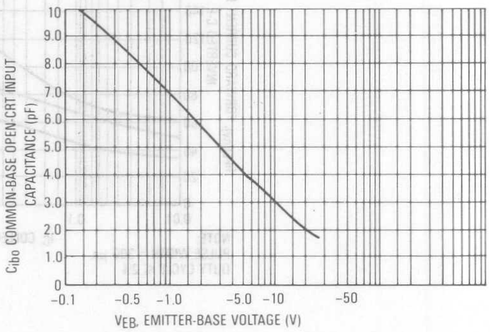


NOTE:
PULSE WIDTH = 300 μs,
DUTY CYCLE ≤ 2%

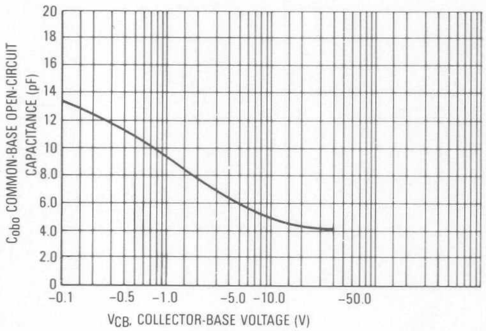
$V_{BE(on)}$ versus I_C



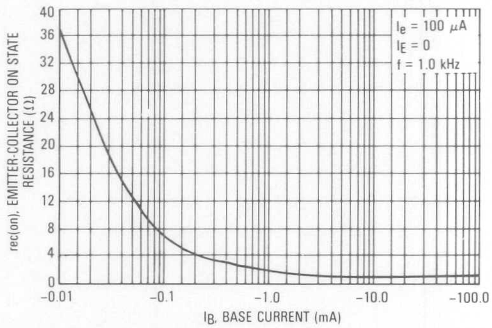
C_{ibo} versus V_{EB}

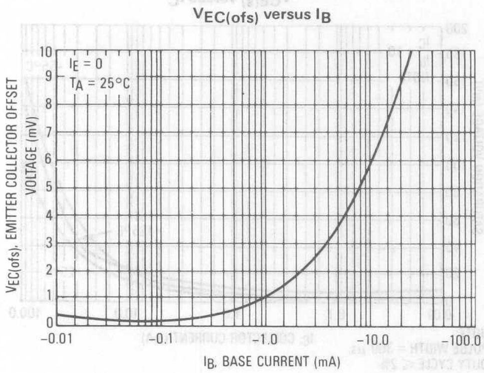


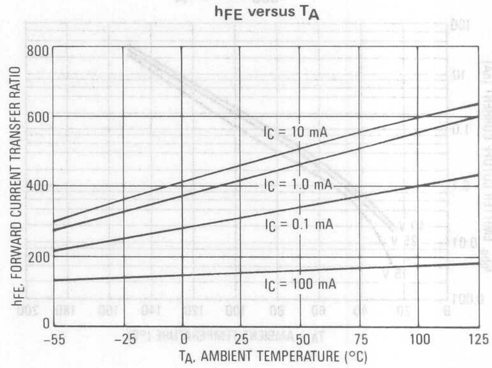
C_{obo} versus V_{CB}

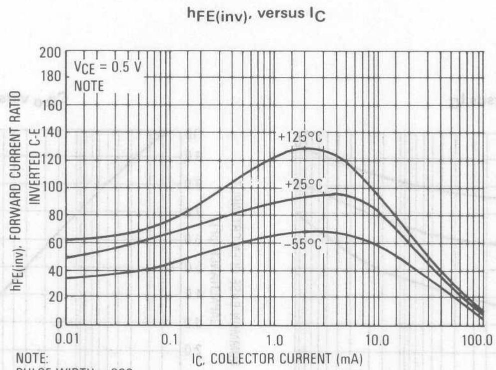


rec(on) versus I_B





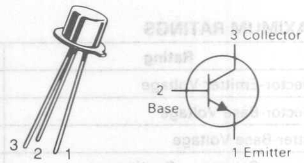




NOTE:
PULSE WIDTH = 300 μs,
DUTY CYCLE ≤ 2%

2N3011

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

NPN SILICON

Refer to 2N2368 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage(1)	V_{CEO}	12	Vdc
Collector-Emitter Voltage	V_{CES}	30	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous Peak (10 μs Pulse)	I_C	200 500	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.36 2.06	Watt mW/°C
Total Device Dissipation @ T_C = 25°C T_C = 100°C Derate above 25°C	P_D	1.20 0.68 6.85	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

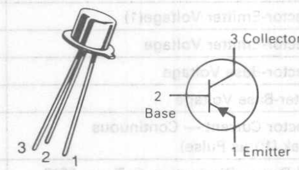
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	12	—	Vdc
Collector-Emitter Breakdown Voltage (I_C = 10 μAdc, V_{BE} = 0)	$V_{(BR)CES}$	30	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	30	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CE} = 20 Vdc V_{BE} = 0) (V_{CE} = 20 Vdc, V_{BE} = 0, T_A = +85°C)	I_{CES}	— —	0.4 10	μAdc
Base Cutoff Current (V_{CE} = 20 Vdc, V_{BE} = 0)	I_{BL}	—	0.4	μAdc
ON CHARACTERISTICS (2)				
DC Current Gain (I_C = 10 mAdc, V_{CE} = 0.35 Vdc) (I_C = 30 mAdc, V_{CE} = 0.4 Vdc) (I_C = 100 mAdc, V_{CE} = 1.0 Vdc)	h_{FE}	30 25 12	120 — 	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 30 mAdc, I_B = 3.0 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc) (I_C = 10 mAdc, I_B = 1.0 mAdc, T_A = +85°C)	$V_{CE(sat)}$	— — — —	0.20 0.25 0.50 0.30	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 30 mAdc, I_B = 3.0 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc)	$V_{BE(sat)}$	0.72 — —	0.87 1.15 1.60	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	400	—	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 140 kHz)	C_{obo}	—	4.0	pF
SWITCHING CHARACTERISTICS				
Storage Time (I_C = I_{B1} = $-I_{B2}$ = 10 mAdc)	t_s	—	13	ns
Turn-On Time (V_{CC} = 2.0 Vdc, $V_{EB(off)}$ = 0, I_C = 30 mAdc, I_{B1} = 3.0 mAdc)	t_{on}	—	15	ns
Turn-Off Time (V_{CC} = 2.0 Vdc, I_C = 30 mAdc, I_{B1} = $-I_{B2}$ = 3.0 mAdc)	t_{off}	—	20	ns

(1) Applicable from 0.01 mA to 10 mA (Pulsed).
(2) Pulse Test: Pulse Length = 30 μs, Duty Cycle ≤ 2.0%.

4

2N3012

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

PNP SILICON

Refer to 2N869A for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	12	Vdc
Collector-Base Voltage	V_{CBO}	12	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.36 2.06	Watts mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.2 6.85	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

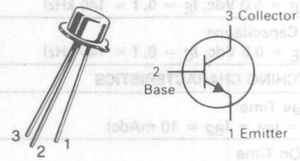
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 10\ \mu Adc$, $V_{BE} = 0$)		$V_{(BR)CES}$	12		Vdc
Collector-Emitter Sustaining Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$) (Emitter-Base Termination — Open Base)		$V_{CEO(sus)}$	12		Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu Adc$, $I_E = 0$)		$V_{(BR)CBO}$	12	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu Adc$, $I_C = 0$)		$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 6.0$ Vdc, $V_{BE} = 0$) ($V_{CE} = 6.0$ Vdc, $V_{BE} = 0$, $T_A = +85°C$)		I_{CES}	— —	80 5.0	μAdc
Base Current ($V_{CE} = 6.0$ Vdc, $V_{BE} = 0$)		I_B	—	30	μAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 10$ mAdc, $V_{CE} = 0.3$ Vdc) ($I_C = 30$ mAdc, $V_{CE} = 0.5$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc)(1)		h_{FE}	 25 30 20	 — 120 —	—
Collector-Emitter Saturation Voltage(1) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 30$ mAdc, $I_B = 3.0$ mAdc) ($I_C = 30$ mAdc, $I_B = 3.0$ mAdc, $T_A = +85°C$) ($I_C = 100$ mAdc, $I_B = 10$ mAdc)		$V_{CE(sat)}$	 — — — —	 0.15 0.2 0.4 0.5	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 30$ mAdc, $I_B = 3.0$ mAdc) ($I_C = 100$ mAdc, $I_B = 10$ mAdc)		$V_{BE(sat)}$	 0.78 0.85 	 0.98 1.2 1.7	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 140 kHz)		C_{obo}	—	6.0	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 140 kHz)		C_{ibo}	—	6.0	pF
Small-Signal Current Gain ($I_C = 30$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)		h_{fe}	4.0	—	—
SWITCHING CHARACTERISTICS					
Turn-On Time	($V_{CC} = 2.0$ Vdc, $I_C \approx 30$ mAdc, $I_{B1} \approx 1.5$ mAdc)	t_{on}	—	60	ns
Turn-Off Time	($V_{CC} = 2.0$ Vdc, $I_C \approx 30$ mAdc, $I_{B1} = I_{B2} \approx 1.5$ mAdc)	t_{off}	—	75	ns

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 1.0%.

2N3013
2N3014

JAN, JTX AVAILABLE
CASE 27-02, STYLE 1
TO-52 (TO-206AC)



SWITCHING TRANSISTOR

NPN SILICON

Refer to 2N3648 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage(1) 2N3013 2N3014	V_{CEO}	 15 20	Vdc
Collector-Emitter Voltage	V_{CES}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous (10 μs pulse) Peak	I_C	200 500	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.36 2.06	Watt mW/°C
Total Device Dissipation @ T_C = 25°C @ T_C = 100°C Derate above 25°C	P_D	1.20 0.68 6.85	Watts Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

(1) Applicable from 0.01 mA to 10 mA (Pulsed)

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 100 μAdc, V_{BE} = 0)		$V_{(BR)CES}$	40	—	Vdc
Collector-Emitter Sustaining Voltage(2) (I_C = 10 mAdc, I_B = 0)	 2N3013 2N3014	$V_{CEO(sus)}$	 15 20	 — —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)		$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	— —	Vdc
Collector Cutoff Current (V_{CE} = 20 Vdc, V_{BE} = 0) (V_{CE} = 20 Vdc, V_{BE} = 0, T_A = +125°C)		I_{CES}	 — —	 0.3 40	μAdc
Base Current (V_{CE} = 20 Vdc, V_{BE} = 0)		I_B	—	0.3	μAdc
ON CHARACTERISTICS(2)					
DC Current Gain (I_C = 30 mAdc, V_{CE} = 0.4 Vdc) (I_C = 100 mAdc, V_{CE} = 0.5 Vdc) (I_C = 10 mAdc, V_{CE} = 0.4 Vdc) (I_C = 300 mAdc, V_{CE} = 1.0 Vdc) (I_C = 100 mAdc, V_{CE} = 1.0 Vdc) (I_C = 30 mAdc, V_{CE} = 0.4 Vdc, T_A = −55°C)	 2N3013 2N3014 2N3013 2N3014	h_{FE}	 30 25 25 15 25 12	 120 — — — — —	—
Collector-Emitter Saturation Voltage (I_C = 30 mAdc, I_B = 3.0 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc) (I_C = 300 mAdc, I_B = 30 mAdc) (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 30 mAdc, I_B = 3.0 mAdc, T_A = +125°C)	 2N3013 2N3014 2N3013 2N3014	$V_{CE(sat)}$	 — — — — — —	 0.18 0.28 0.35 0.50 0.18 0.25	Vdc
Base-Emitter Saturation Voltage (I_C = 30 mAdc, I_B = 3.0 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc) (I_C = 300 mAdc, I_B = 30 mAdc) (I_C = 10 mAdc, I_B = 1.0 mAdc)	 2N3013 2N3014	$V_{BE(sat)}$	 0.75 — — 0.70	 0.95 1.20 1.70 0.80	Vdc

4

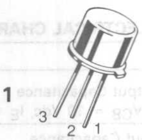
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 30 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	350	—	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 140 kHz)		C_{obo}	—	5.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 140 kHz)		C_{ibo}	—	8.0	pF
SWITCHING CHARACTERISTICS					
Storage Time (I_C = I_{B1} = I_{B2} = 10 mAdc)		t_s	—	18	ns
Turn-On Time ($V_{EB(off)}$ = 5.0 V, V_{CC} = 15 V, I_C = 300 mAdc, I_{B1} = 30 mAdc)	2N3013	t_{on}	—	15	ns
($V_{EB(off)}$ = 0, V_{CC} = 2.0 V, I_C = 30 mAdc, I_{B1} = 3.0 mAdc)	2N3014		—	16	
Turn-Off Time (V_{CC} = 15 V, I_C = 300 mAdc, I_{B1} = I_{B2} = 30 mAdc)	2N3013	t_{off}	—	25	ns
(V_{CC} = 2.0 V, I_C = 30 mAdc, I_{B1} = I_{B2} = 3.0 mAdc)	2N3014		—	25	

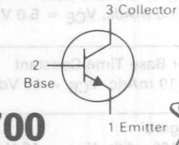
(2) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

2N3019
2N3020

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



JAN, JTX, JTXV AVAILABLE



2N3700

CASE 22-03, STYLE 1
TO-18 (TO-206AA)

GENERAL TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	2N3019 2N3020	2N3700	Unit
Collector-Emitter Voltage	V_{CEO}	80	80	Vdc
Collector-Base Voltage	V_{CBO}	140	140	Vdc
Emitter-Base Voltage	V_{EBO}	7.0	7.0	Vdc
Collector Current — Continuous	I_C	1.0	1.0	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.8 4.6	0.5 2.85	Watts mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5.0 28.6	1.8 10.6	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	2N3019 2N3020	2N3700	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	16.5	70	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	89.5	245	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

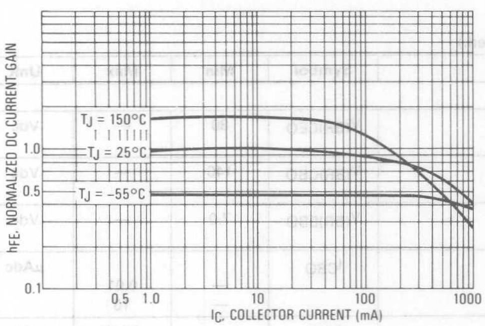
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 30$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	80	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)		$V_{(BR)CBO}$	140	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	7.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 90$ Vdc, $I_E = 0$) ($V_{CB} = 90$ Vdc, $I_E = 0$, $T_A = +150°C$)		I_{CBO}	 — —	 0.01 10	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$)		I_{EBO}	—	0.010	μAdc
ON CHARACTERISTICS					
DC Current Gain(1) ($I_C = 0.1$ mAdc, $V_{CE} = 10$ Vdc)	 2N3700, 2N3019 2N3020	h_{FE}	 50 30	 — 100	—
($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc)	2N3700, 2N3019 2N3020		90 40	— 120	
($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)	2N3700, 2N3019 2N3020		100 40	300 120	
($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc, $T_C = -55°C$)	2N3700, 2N3019		40	—	
($I_C = 500$ mAdc, $V_{CE} = 10$ Vdc)	2N3700, 2N3019 2N3020		50 30	— 100	
($I_C = 1.0$ Adc, $V_{CE} = 10$ Vdc)	All Types		15	—	
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)		$V_{CE(sat)}$	 — —	 0.2 0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)		$V_{BE(sat)}$	—	1.1	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)	 2N3020 2N3019, 2N3700	f_T	 80 100	 — 400	MHz

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

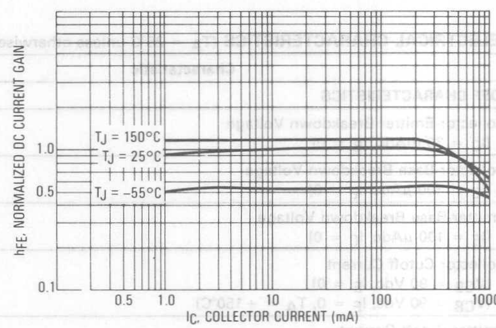
Characteristic		Symbol	Min	Max	Unit
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	12	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	60	pF
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)		h_{fe}			—
	2N3700, 2N3019		80	400	
	2N3020		30	200	
Collector Base Time Constant (I_E = 10 mAdc, V_{CB} = 10 Vdc, f = 79.8 MHz)		$r_b'C_c$			ps
	2N3019, 2N3020		—	400	
	2N3700		15	400	
Noise Figure (I_C = 100 μAdc, V_{CE} = 10 Vdc, R_S = 1.0 k ohms, f = 1.0 kHz)	2N3019, 2N3700	NF	—	4	dB

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 1.0%.

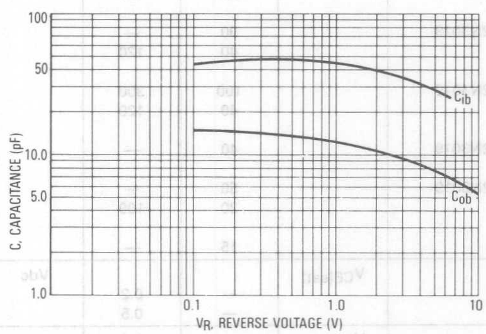
DC CURRENT GAIN 2N3019, 2N3700



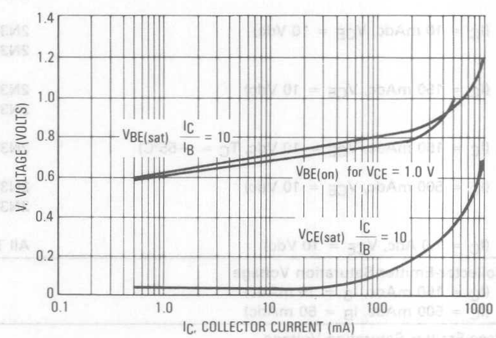
DC CURRENT GAIN 2N3020

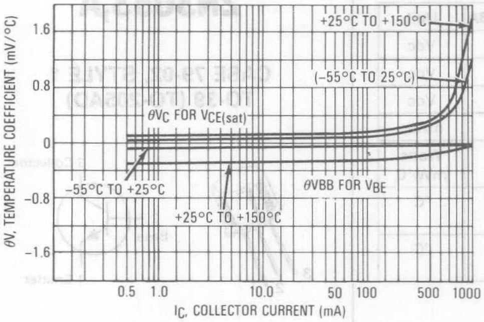


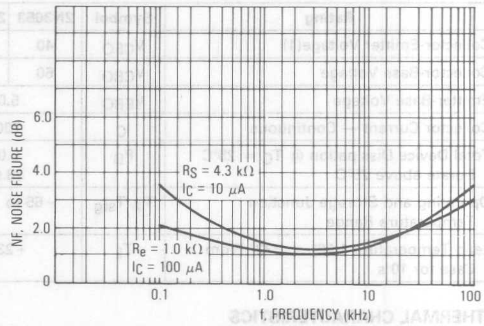
CAPACITANCE



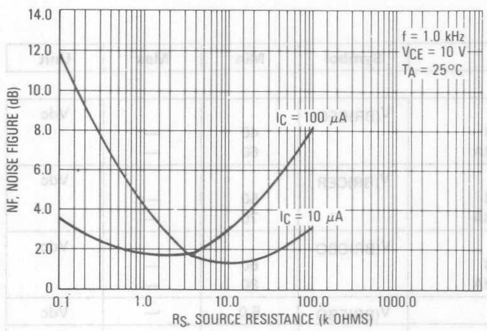
"ON" VOLTAGES



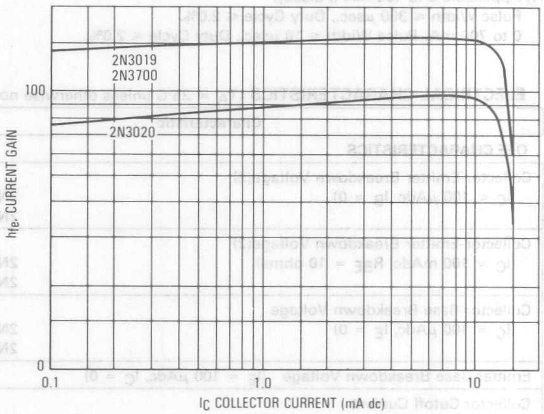




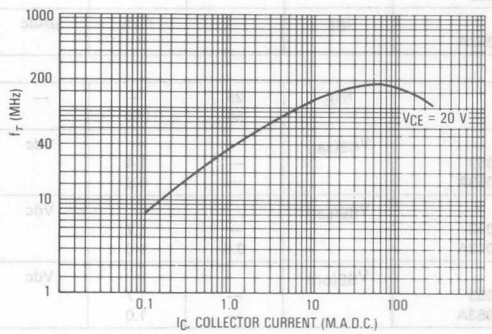
SOURCE RESISTANCE EFFECTS



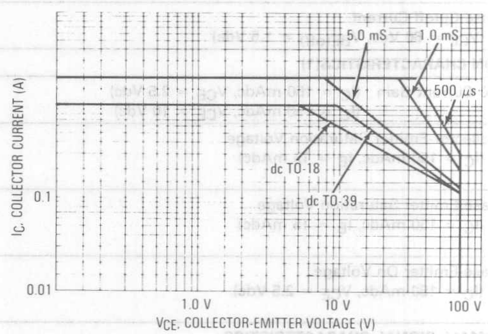
CURRENT GAIN BANDWIDTH PRODUCT versus COLLECTOR CURRENT — 1 kHz h_{fe}



CURRENT GAIN — BANDWIDTH PRODUCT



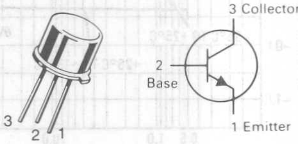
ACTIVE REGION SAFE OPERATING AREA



4

2N3053,A

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N3019 for graphs.

MAXIMUM RATINGS

Rating	Symbol	2N3053	2N3053A	Unit
Collector-Emitter Voltage(1)	V_{CEO}	40	60	Vdc
Collector-Base Voltage	V_{CBO}	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	700		mAdc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	5.0 28.6		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C
Lead Temperature 1/16″, ±1/32″ From Case for 10 s	T_L	+235		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W

(1) Applicable 0 to 100 mA (Pulsed):
Pulse Width ≤ 300 μsec., Duty Cycle ≤ 2.0%.
0 to 700 mA; Pulse Width ≤ 10 μsec., Duty Cycle ≤ 2.0%.

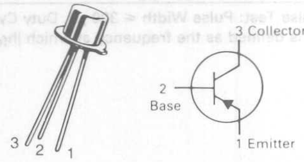
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 100 μAdc, I_B = 0)	2N3053 2N3053A	$V_{(BR)CEO}$	40 60	— —	Vdc
Collector-Emitter Breakdown Voltage(2) (I_C = 100 mAdc, R_{BE} = 10 ohms)	2N3053 2N3053A	$V_{(BR)CER}$	50 70	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	2N3053 2N3053A	$V_{(BR)CBO}$	60 80	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CE} = 30 Vdc, $V_{BE(off)}$ = 1.5 Vdc) (V_{CE} = 60 Vdc, $V_{BE(off)}$ = 1.5 Vdc)	 2N3053 2N3053A	I_{CEX}	—	0.25	μAdc
Emitter Cutoff Current (V_{BE} = 4.0 Vdc, I_C = 0)	2N3053	I_{EBO}	—	0.25	μAdc
Base Cutoff Current (V_{CE} = 60 Vdc, $V_{BE(off)}$ = 1.5 Vdc)	2N3053A	I_{BL}	—	0.25	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 150 mAdc, V_{CE} = 2.5 Vdc) (I_C = 150 mAdc, V_{CE} = 10 Vdc)		h_{FE}	25 50	— 250	—
Collector-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	2N3053 2N3053A	$V_{CE(sat)}$	— —	1.4 0.3	Vdc
Base-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	2N3053 2N3053A	$V_{BE(sat)}$	— 0.6	1.7 1.0	Vdc
Base-Emitter On Voltage (I_C = 150 mAdc, V_{CE} = 2.5 Vdc)	2N3053 2N3053A	$V_{BE(on)}$	— —	1.7 1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)		f_T	100	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 140 kHz)		C_{obo}	—	15	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 140 kHz)		C_{ibo}	—	80	pF

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2N3073

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

PNP SILICON

4

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	60	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	500	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	360 2.06	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.2 6.85	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

Refer to 2N2904 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

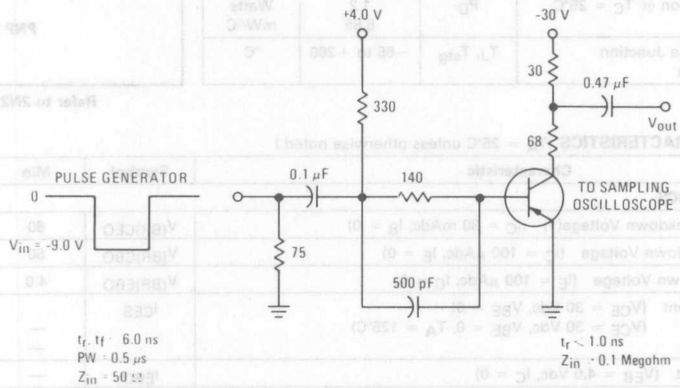
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 30$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	60	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 30$ Vdc, $V_{BE} = 0$) ($V_{CE} = 30$ Vdc, $V_{BE} = 0$, $T_A = 125°C$)	I_{CES}	— —	10 10	nAdc μAdc
Emitter Cutoff Current ($V_{EB} = 4.0$ Vdc, $I_C = 0$)	I_{EBO}	—	100	μAdc
Base Current ($V_{CE} = 30$ Vdc, $V_{BE} = 0$)	I_B	—	10	nAdc
ON CHARACTERISTICS				
DC Current Gain(1) ($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc, $T_A = -55°C$) ($I_C = 300$ mAdc, $V_{CE} = 2.0$ Vdc)	h_{FE}	30 12 15	130 — —	—
Collector-Emitter Saturation Voltage ($I_C = 50$ mAdc, $I_B = 2.5$ mAdc) ($I_C = 300$ mAdc, $I_B = 30$ mAdc)	$V_{CE(sat)}$	— —	0.25 1.0	Vdc
Base-Emitter Saturation Voltage ($I_C = 50$ mAdc, $I_B = 2.5$ mAdc) ($I_C = 300$ mAdc, $I_B = 30$ mAdc)	$V_{BE(sat)}$	— —	1.2 2.0	Vdc
Base-Emitter On Voltage ($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc)	$V_{BE(on)}$	—	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product(2) ($I_C = 50$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)	f_T	130	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 140 kHz)	C_{obo}	—	10	pF
Input Impedance ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{ie}	—	1.5	kohms
Voltage Feedback Ratio ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{re}	—	26	$X\ 10^{-4}$
Small Signal Current Gain ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	25	180	—
Output Admittance ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{oe}	—	1200	μmhos

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

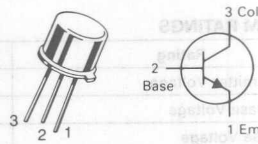
Characteristic	Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS				
Turn-On Time (I_C≈300 mAdc, I_{B1}≈30 mAdc)	t_{on}	—	40	ns
Turn-Off Time (I_C≈300 mAdc, I_{B1}≈I_{B2}≈30 mAdc)	t_{off}	—	100	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 1.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

FIGURE 1 – TURN-ON AND TURN-OFF SWITCHING TIMES TEST CIRCUIT



CASE 79-02, STYLE 1
TO-39 (TO-205AD)



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage(1)	V_{CEO}	150	Vdc
Collector-Base Voltage	V_{CBO}	150	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.8 4.57	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5.0 28.6	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N3498 for graphs.

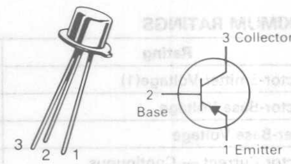
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(2) (I_C = = 30 mAdc, $I_B = 0$)	$V_{(BR)CEO}$	150	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu Adc$, $I_E = 0$)	$V_{(BR)CBO}$	150	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu Adc$, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 100$ Vdc, $I_E = 0$) ($V_{CB} = 100$ Vdc, $I_E = 0$, $T_A = 150°C$)	I_{CBO}	 — —	 0.010 10	μAdc
Emitter Cutoff Current ($V_{EB} = 4.0$ Vdc, $I_C = 0$)	I_{EBO}	—	0.10	μAdc
ON CHARACTERISTICS				
DC Current Gain(2) ($I_C = 0.1$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 30$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 30$ mAdc, $V_{CE} = 10$ Vdc, $T_A = -55°C$)	h_{FE}	 15 30 12	 — 120 —	—
Collector-Emitter Saturation Voltage(2) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)	$V_{CE(sat)}$	—	1.0	Vdc
Base-Emitter Saturation Voltage(2) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)	$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance ($V_{CB} = 20$ Vdc, $I_E = 0$, f = 140 kHz)	C_{obo}	—	9.0	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 140 kHz)	C_{ibo}	—	80	pF
Small-Signal Current Gain ($I_C = 1.0$ mA, $V_{CE} = 5.0$ V, f = 1 kHz)	h_{fe}	25	—	—
Current Gain — High Frequency ($V_{CE} = 10$ Vdc, $I_C = 30$ mAdc, f = 20 MHz)	$\lvert h_{fe}\rvert$	2.0	—	—
Real Part of Input Impedance ($I_C = 10$ mA, $V_{CE} = 10$ V, f = 100 MHz)	$Re(h_{ie})$	—	30	Ohms

(1) Between 0 and 30 mA.
(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 1.0%.

2N3135

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

PNP SILICON

Refer to 2N2904 for graphs.

4

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	35	Vdc
Collector-Base Voltage	V_{CBO}	50	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	600	mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.4 2.28	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.8 10.3	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

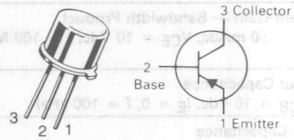
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	35	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	50	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 30$ V, $V_{BE} = 0.5$ V)	I_{CEX}	—	0.1	μAdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$) ($V_{CB} = 30$ Vdc, $I_E = 0$, $T_A = 150°C$)	I_{CBO}	 — —	 0.05 30	μAdc
Base Cutoff Current ($V_{CE} = 30$ V, $V_{BE} = 0.5$ V)	I_{BL}	—	0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)(1)	h_{FE}	 25 40	 — 120	—
Collector-Emitter Saturation Voltage(1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{CE(sat)}$	—	0.6	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{BE(sat)}$	—	1.5	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)	f_T	200	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	10	pF
Input Capacitance ($V_{BE} = 2$ Vdc, $I_C = 0$, f = 100 kHz)	C_{ibo}	—	40	pF
SWITCHING CHARACTERISTICS				
Turn-On Time ($V_{CC} = 30$ V, $I_C = 150$ mA, $I_{B1} = 15$ mA)	t_{on}	26	75	ns
Turn-Off Time ($V_{CC} = 6.0$ V, $I_C = 150$ mA, $I_{B1} = I_{B2} = 15$ mA)	t_{off}	70	150	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2N3227 For Specifications, See 2N2368 Data.

2N3244
2N3245

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	2N3244	2N3245	Unit
Collector-Emitter Voltage	V_{CEO}	40	50	Vdc
Collector-Base Voltage	V_{CBO}	40	50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	1.0		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 5.71		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5.0 28.6		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	0.175	°C/mW

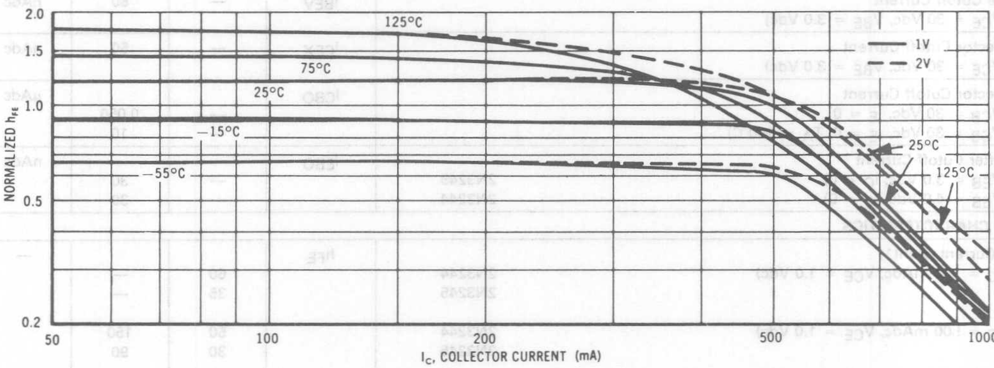
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	 2N3244 2N3245	$V_{(BR)CEO}$	 40 50	 — —	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	 2N3244 2N3245	$V_{(BR)CBO}$	 40 50	 — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Base Cutoff Current (V_{CE} = 30 Vdc, V_{BE} = 3.0 Vdc)		I_{BEV}	—	80	nAdc
Collector Cutoff Current (V_{CE} = 30 Vdc, V_{BE} = 3.0 Vdc)		I_{CEX}	—	50	nAdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0) (V_{CB} = 30 Vdc, I_E = 0, T_A = 100°C)		I_{CBO}	 — —	 0.050 10	μAdc
Emitter Cutoff Current (V_{EB} = 3.0 Vdc, I_C = 0) (V_{EB} = 4.0 Vdc, I_C = 0)	 2N3245 2N3244	I_{EBO}	 — —	 30 30	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 150 mAdc, V_{CE} = 1.0 Vdc)	 2N3244 2N3245	h_{FE}	 60 35	 — —	—
(I_C = 500 mAdc, V_{CE} = 1.0 Vdc)	2N3244 2N3245		50 30	150 90	
(I_C = 1.0 Adc, V_{CE} = 5.0 Vdc)	2N3244 2N3245		25 20	— —	
Collector-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc)	 2N3244 2N3245	$V_{CE(sat)}$	 — —	 0.3 0.35	Vdc
(I_C = 500 mAdc, I_B = 50 mAdc)	2N3244 2N3245		— —	0.5 0.6	
(I_C = 1.0 Adc, I_B = 100 mAdc)	2N3244 2N3245		— —	1.0 1.2	

Characteristic	Conditions	Device	Symbol	Min	Max	Unit
Base-Emitter Saturation Voltage(1)			$V_{BE(sat)}$			Vdc
	(I_C = 150 mAdc, I_B = 15 mAdc)			—	1.1	
	(I_C = 500 mAdc, I_B = 50 mAdc)			0.75	1.5	
	(I_C = 1.0 Adc, I_B = 100 mAdc)			—	2.0	
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product	(I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	2N3244	f_T	175		MHz
		2N3245		150		
Output Capacitance	(V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	25	pF
Input Capacitance	(V_{EB} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	100	pF
SWITCHING CHARACTERISTICS						
Delay Time	(I_C = 500 mA, I_{B1} = 50 mA, V_{EB} = 2.0 V, V_{CC} = 30 V)		t_d	—	15	ns
Rise Time		2N3244	t_r	—	35	ns
		2N3245		—	40	
Storage Time	(I_C = 500 mA, V_{CC} = 30 V, I_{B1} = I_{B2} = 50 mA)	2N3244	t_s	—	140	ns
		2N3245			120	
Fall Time			t_f	—	45	ns
Total Control Charge	(I_C = 500 mA, I_B = 50 mA, V_{CC} = 30 V)	2N3244	Q_T		14	pC
		2N3245		—	12	

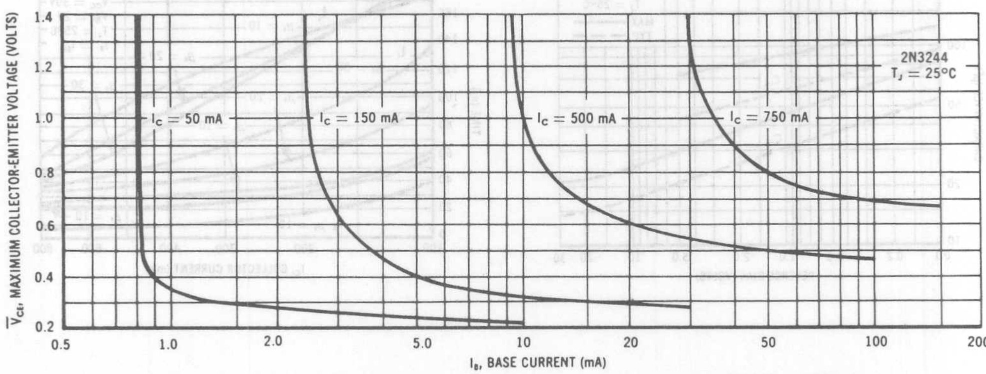
(1) Pulse Test: PW ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — MINIMUM CURRENT GAIN CHARACTERISTICS



4

FIGURE 2 — COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS



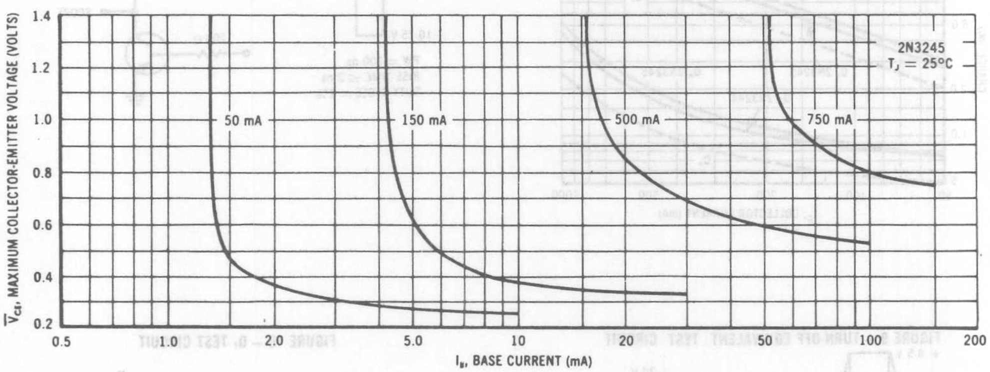


FIGURE 3 — MAXIMUM SATURATION VOLTAGES

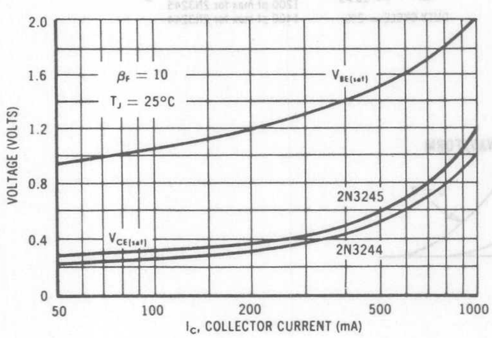


FIGURE 4 — TYPICAL TEMPERATURE COEFFICIENTS

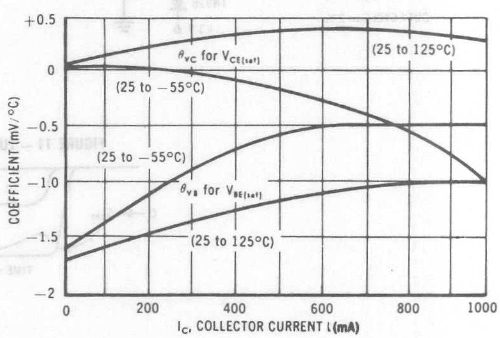


FIGURE 5 — JUNCTION CAPACITANCE

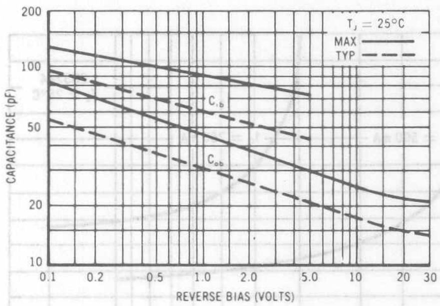


FIGURE 6 — TYPICAL SWITCHING TIMES

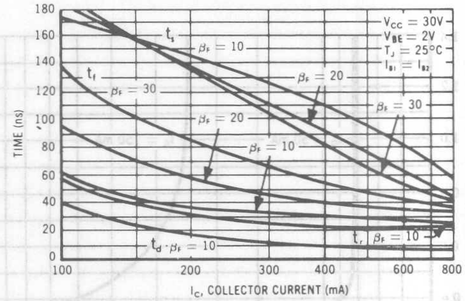


FIGURE 7 — CHARGE DATA

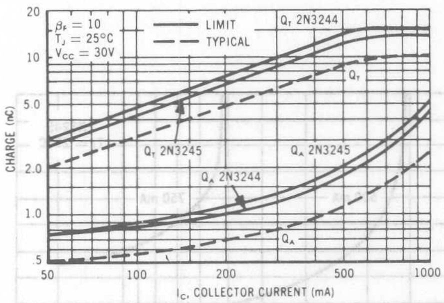


FIGURE 8 — TURN-ON EQUIVALENT TEST CIRCUIT

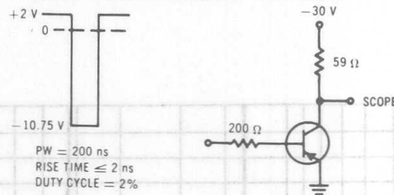


FIGURE 9 — TURN-OFF EQUIVALENT TEST CIRCUIT

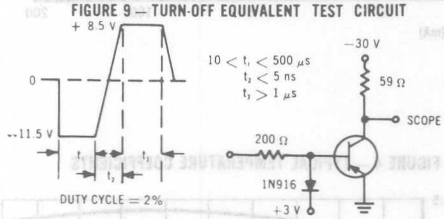


FIGURE 10 — Q_T TEST CIRCUIT

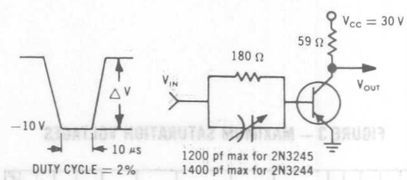
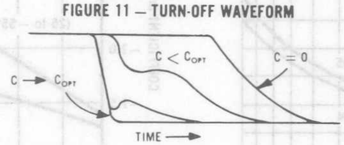
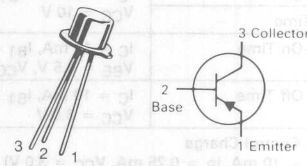


FIGURE 11 — TURN-OFF WAVEFORM



2N3249

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	12	Vdc
Collector-Base Voltage	V_{CBO}	15	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	200	mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.36 2.06	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.2 6.9	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	12	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	15	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Base Cutoff Current ($V_{CE} = 10$ Vdc, $V_{BE} = 1.0$ Vdc)	I_{BEV}	—	50	nAdc
Collector Cutoff Current ($V_{CE} = 10$ Vdc, $V_{BE} = 1.0$ Vdc) ($V_{CE} = 10$ Vdc, $V_{BE} = 1.0$ Vdc, $T_A = 100°C$)	I_{CEX}	 —	 0.05 5.0	μAdc
ON CHARACTERISTICS				
DC Current Gain(1) ($I_C = 0.1$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	 100 100 100 75 35	 300 — — — —	—
Collector-Emitter Saturation Voltage(1) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc) ($I_C = 100$ mAdc, $I_B = 10$ mAdc)	$V_{CE(sat)}$	 — — —	 0.125 0.25 0.45	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc) ($I_C = 100$ mAdc, $I_B = 10$ mAdc)	$V_{BE(sat)}$	 0.6 0.7 —	 0.9 1.1 1.3	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 20$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	300	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	8.0	pF
Input Capacitance ($V_{BE} = 1.0$ Vdc, $I_C = 0$, f = 100 kHz)	C_{ibo}	—	8.0	pF

SWITCHING CHARACTERISTICS

Characteristic	Conditions	Symbol	Min	Max	Unit
Delay Time	I_C = 100 mA, I_B = 10 mA, V_{BE} = 0.5 V, V_{CC} = 10 V	t_d	—	5.0	ns
Rise Time		t_r	—	15	ns
Storage Time	I_C = 100 mA, I_{B1} = I_{B2} = 10 mA, V_{CC} = 10 V	t_s	—	60	ns
Fall Time		t_f	—	20	ns
Turn-On Time	I_C = 10 mA, I_{B1} = 1.0 mA, V_{BE} = 0.5 V, V_{CC} = 3.0 V	t_{on}	—	90	ns
Turn-Off Time	I_C = 10 mA, I_{B1} = I_{B2} = 1.0 mA, V_{CC} = 3.0 V	t_{off}	—	100	ns
Total Control Charge (I_C = 10 mA, I_B = 0.25 mA, V_{CC} = 3.0 V)		Q_T	—	150	pC

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

4

FIGURE 1 — t_{on} CIRCUIT

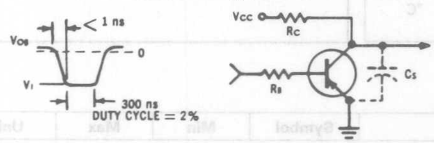
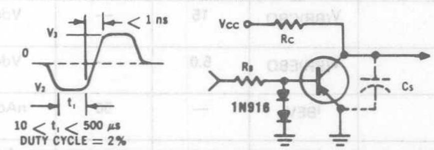


FIGURE 2 — t_{off} CIRCUIT



I_C mA	V_{CC} volts	R_B ohms	R_C ohms	$C_{S(max)}$* pF	V_{OB} volts	V_1 volts	V_2 volts	V_3 volts
10	3	10 K	285	4	+0.5	−10.6	−10.9	+9.1
100	10	1 K	95	12	+0.5	−10.7	−11.3	+8.7

*Total shunt capacitance of test jig and connectors.

FIGURE 3 — TYPICAL SWITCHING TIMES

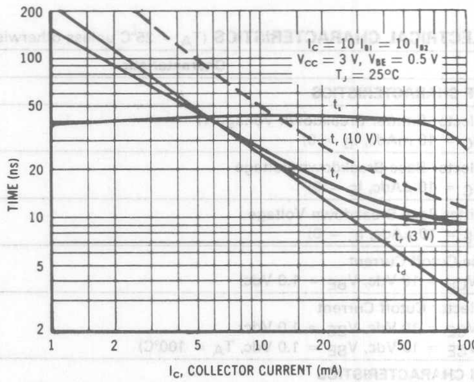
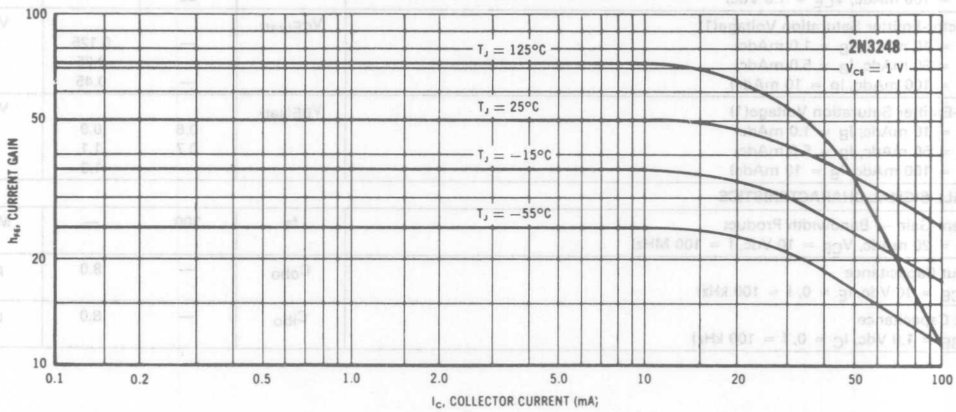


FIGURE 4 — MINIMUM CURRENT GAIN CHARACTERISTICS



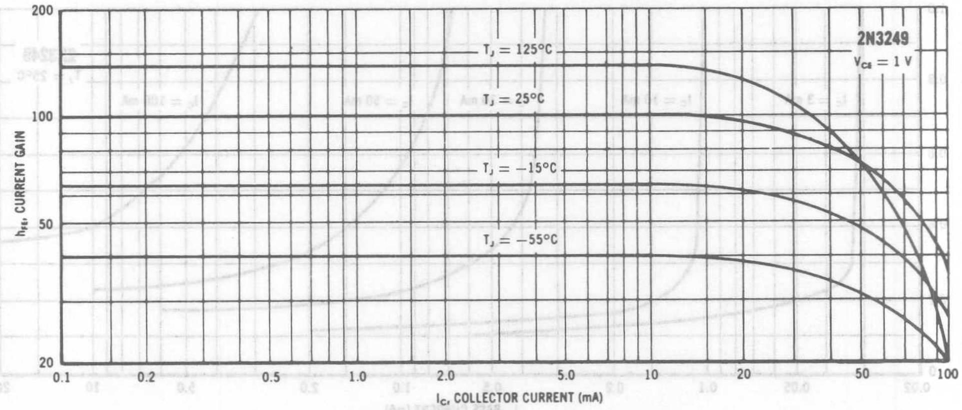


FIGURE 5 — MAXIMUM CHARGE DATA

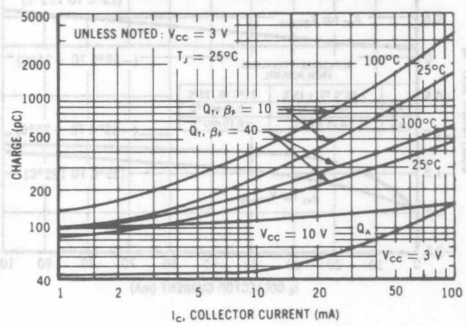


FIGURE 6 — JUNCTION CAPACITANCE

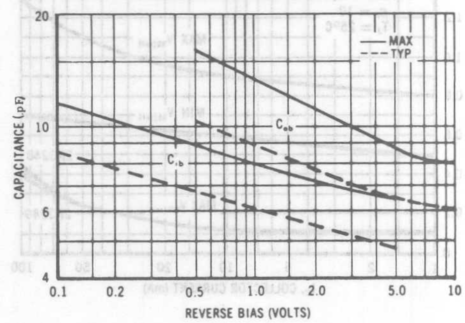
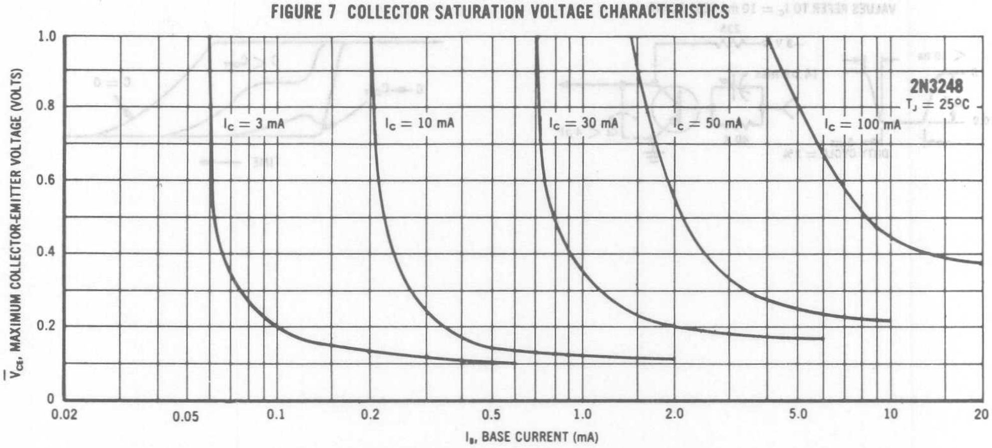


FIGURE 7 COLLECTOR SATURATION VOLTAGE CHARACTERISTICS



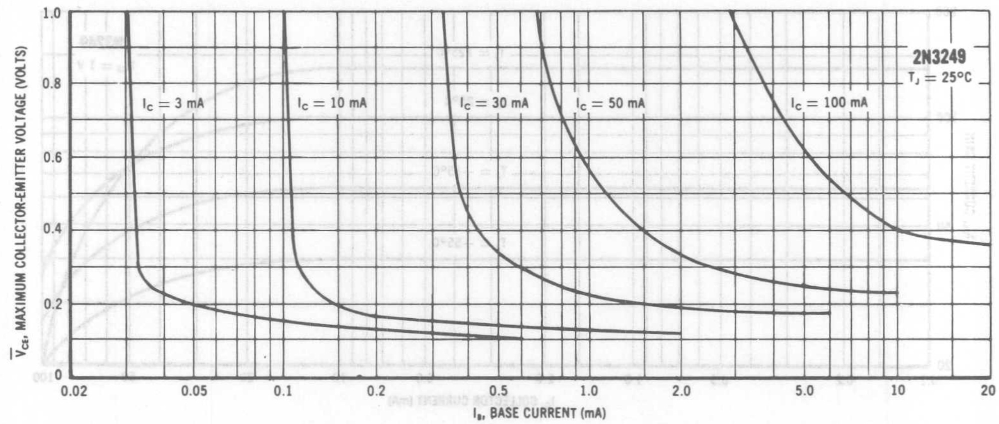


FIGURE 8 — SATURATION VOLTAGE LIMITS

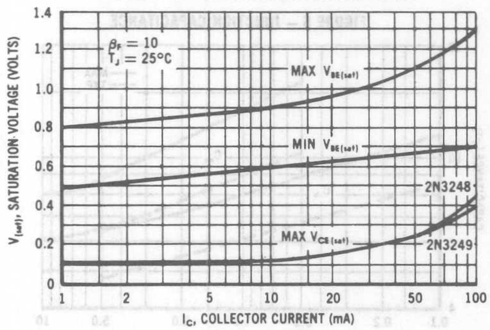


FIGURE 9 — TYPICAL TEMPERATURE COEFFICIENTS

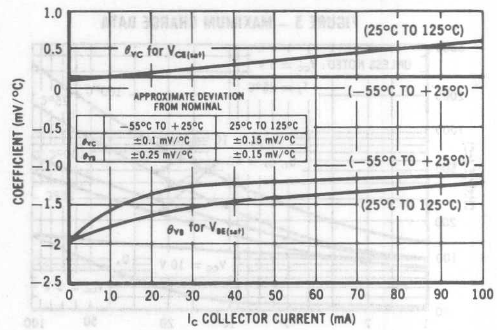


FIGURE 10 — Q_T TEST CIRCUIT

VALUES REFER TO $I_C = 10$ mA TEST POINT

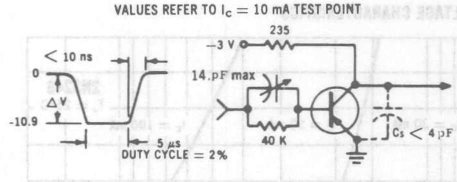
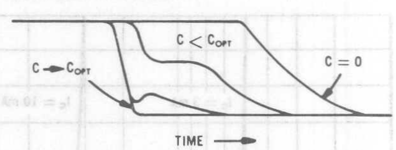
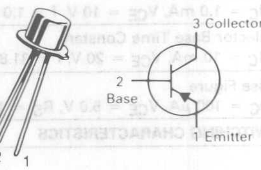


FIGURE 11 — TURN-OFF WAVE FORM



2N3250,A
2N3251,A

2N3250A,2N3251A
JAN, JTX, JTXV AVAILABLE
CASE 22-03, STYLE 1
TO-18 (TO-206AA)



GENERAL PURPOSE TRANSISTORS
PNP SILICON

4

MAXIMUM RATINGS

Rating	Symbol	2N3250 2N3251	2N3250A 2N3251A	Unit
Collector-Emitter Voltage	V_{CEO}	40	60	Vdc
Collector-Base Voltage	V_{CBO}	50	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current	I_C	200		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.36 2.06		Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.2 6.9		Watts mW/°C
Operating and Storage Temperature Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.15	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	0.49	mW/°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (1) (I_C = 10 mAdc)	2N3250, 2N3251 2N3250A, 2N3251A	$V_{(BR)CEO}$	40 60	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc)	2N3250, 2N3251 2N3250A, 2N3251A	$V_{(BR)CBO}$	50 60	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CE} = 40 Vdc, V_{BE} = 3.0 Vdc)		I_{CEX}		20	Adc
Base Cutoff Current (V_{CE} = 40 Vdc, V_{BE} = 3.0 Vdc)		I_{BL}	—	50	nAdc
ON CHARACTERISTICS					
DC Forward Current Transfer Radio (1)		h_{FE}			—
(I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc)	2N3250, 2N3250A 2N3251, 2N3251A		40 80	— —	
(I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc)	2N3250, 2N3250A 2N3251, 2N3251A		45 90	— —	
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	2N3250, 2N3250A 2N3251, 2N3251A		50 100	150 300	
(I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	2N3250, 2N3250A 2N3251, 2N3251A		15 30	— —	
Collector-Emitter Saturation Voltage (1) (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{CE(sat)}$	— —	0.25 0.5	Vdc
Base-Emitter Saturation Voltage (1) (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{BE(sat)}$	0.6 —	0.9 1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	2N3250, 2N3250A 2N3251, 2N3251A	f_T	250 300	— —	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	6.0	pF
Input Capacitance (V_{CB} = 1.0 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	8.0	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Input Impedance (I_C = 1.0 mA, V_{CE} = 10 V, f = 1.0 kHz)	2N3250, 2N3250A 2N3251, 2N3251A	h_{ie}	1.0 2.0	6.0 12	kohms
Voltage Feedback Ratio (I_C = 1.0 mA, V_{CE} = 10 V, f = 1.0 kHz)	2N3250, 2N3250A 2N3251, 2N3251A	h_{re}	— —	10 20	X 10^{-4}
Small-Signal Current Gain (I_C = 1.0 mA, V_{CE} = 10 V, f = 1.0 kHz)	2N3250, 2N3250A 2N3251, 2N3251A	h_{fe}	50 100	200 400	—
Output Admittance (I_C = 1.0 mA, V_{CE} = 10 V, f = 1.0 kHz)	2N3250, 2N3250A 2N3251, 2N3251A	h_{oe}	4.0 10	40 60	μmhos
Collector Base Time Constant (I_C = 10 mA, V_{CE} = 20 V, f = 31.8 MHz)		$rb'C_C$	—	250	ps
Noise Figure (I_C = 100 μA, V_{CE} = 5.0 V, R_S = 1.0 k Ω, f = 100 Hz)		NF	—	6.0	dB

SWITCHING CHARACTERISTICS

Characteristic			Symbol	Max	Unit
Delay Time	(V_{CC} = 3.0 Vdc, V_{BE} = 0.5 Vdc		t_d	35	ns
Rise Time	I_C = 10 mAdc, I_{B1} = 1.0 mA)		t_r	35	ns
Storage Time	(I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc V_{CC} = 3.0 V)	2N3250, 2N3250A 2N3251, 2N3251A	t_s	175 200	ns
Fall Time			t_f	50	ns

(1) Pulse Test: PW = 300 μs, Duty Cycle = 2.0%.

SWITCHING TIME CHARACTERISTICS

FIGURE 1 — DELAY AND RISE TIME

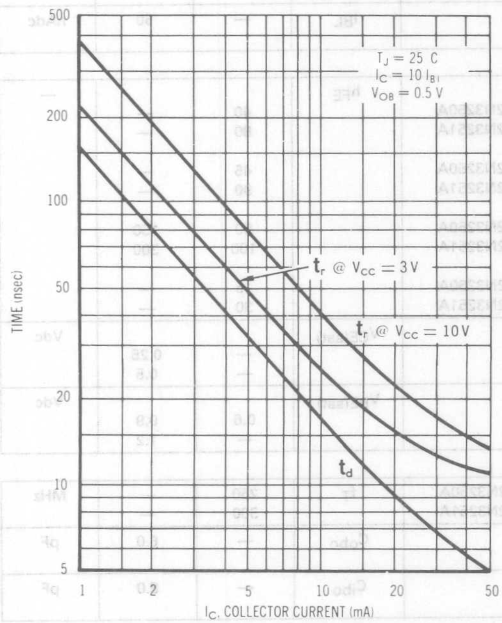
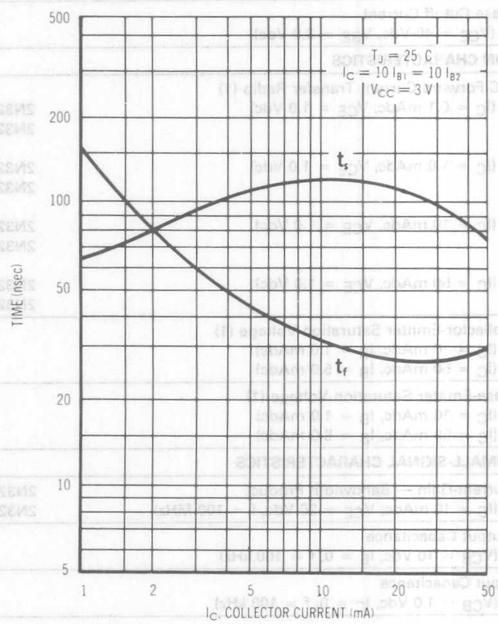


FIGURE 2 — STORAGE AND FALL TIME



($V_{CE} = 6$ V, $T_A = 25°C$)

FIGURE 3 — FREQUENCY

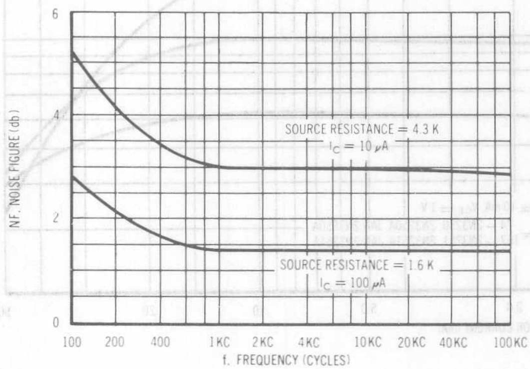
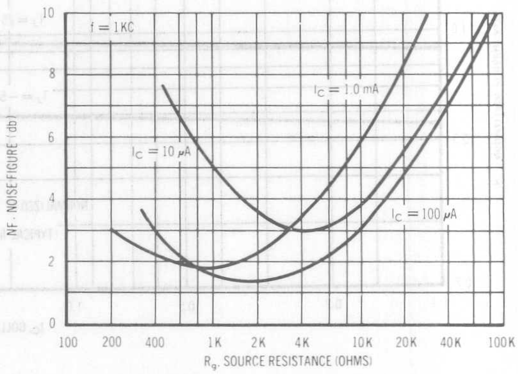


FIGURE 4 — SOURCE RESISTANCE



4

h PARAMETERS

$V_{CE} = 10$ V, f = 1 kc, $T_A = 25°C$

FIGURE 5 — CURRENT GAIN

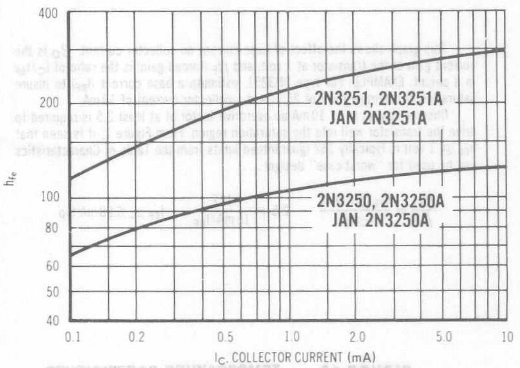


FIGURE 6 — OUTPUT ADMITTANCE

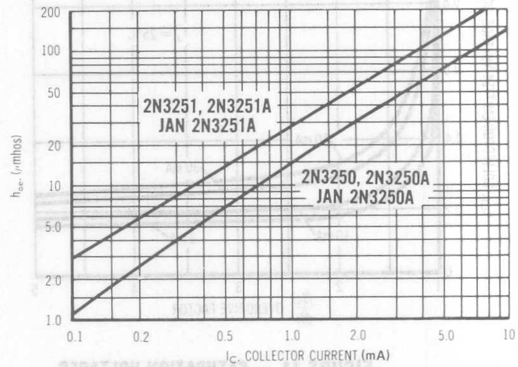


FIGURE 7 — VOLTAGE FEEDBACK RATIO

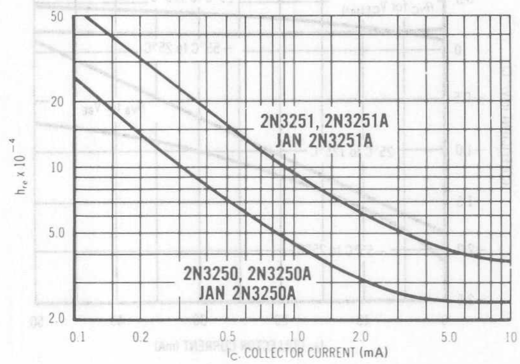


FIGURE 8 — INPUT IMPEDANCE

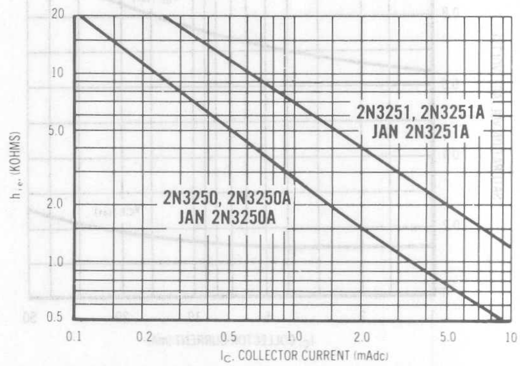


FIGURE 9 — NORMALIZED CURRENT GAIN CHARACTERISTICS

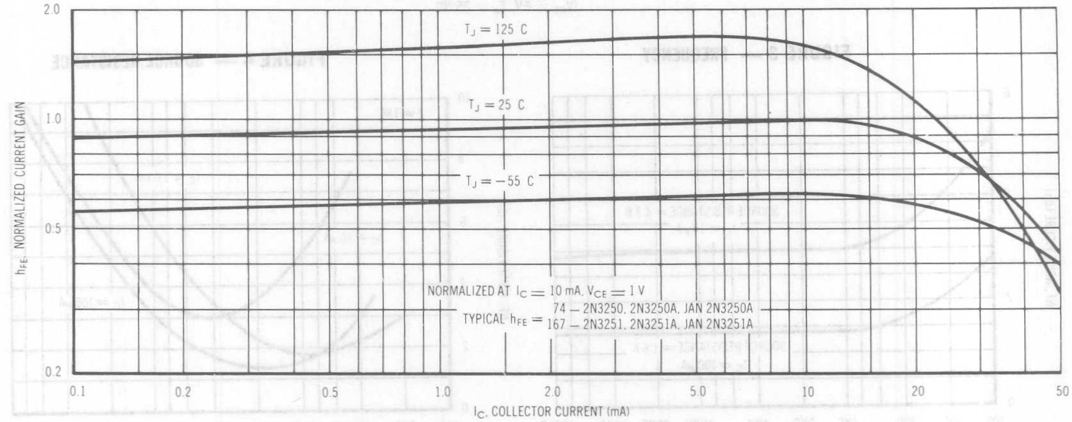
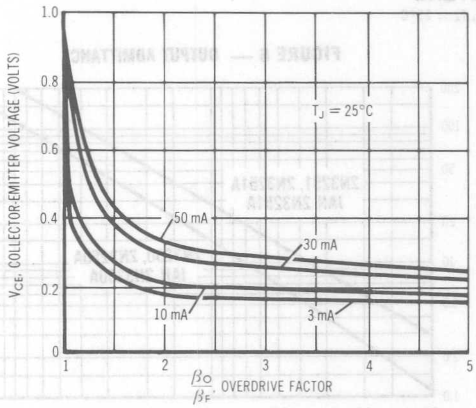


FIGURE 10 — COLLECTOR SATURATION REGION



This graph shows the effect of base current on collector current. β_O is the current gain of the transistor at 1 volt, and β_F (forced gain) is the ratio of I_C/I_{BF} in a circuit. EXAMPLE: For type 2N3251, estimate a base current (I_{BF}) to insure saturation at a temperature of 25°C and a collector current of 10 mA.

Observe that at $I_C = 10$ mA an overdrive factor of at least 2.5 is required to drive the transistor well into the saturation region. From Figure 1, it is seen that h_{FE} @ 1 volt is typically 167 (guaranteed limits from the Table of Characteristics can be used for "worst-case" design) . . .

$$\frac{\beta_O}{\beta_F} = \frac{h_{FE}\ @\ 1\ \text{Volt}}{I_C/I_{BF}} \qquad 2.5 = \frac{167}{10\ \text{mA}/I_{BF}} \qquad I_{BF} \approx 6.68\ \text{mA typ}$$

FIGURE 11 — SATURATION VOLTAGES

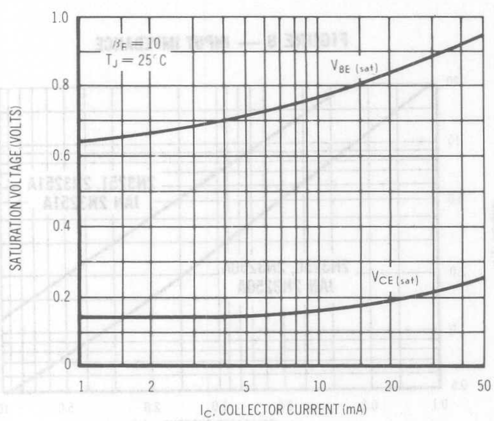


FIGURE 12 — TEMPERATURE COEFFICIENTS

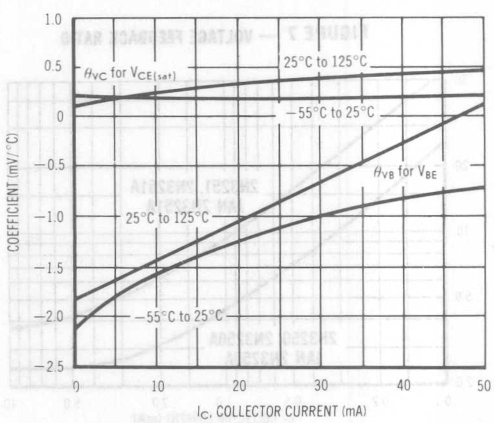


FIGURE 13 — f_T AND $r_b'C_C$ versus I_C

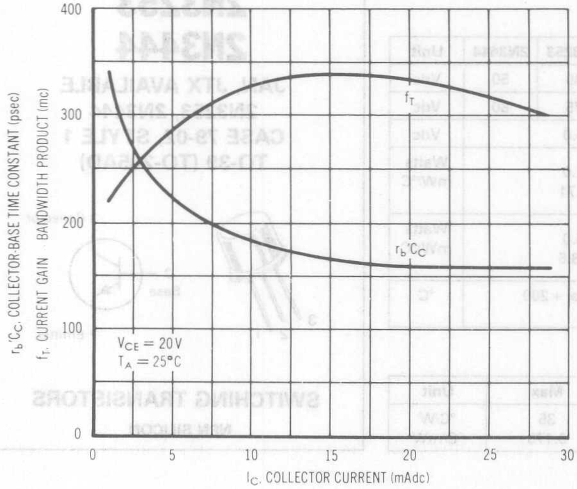


FIGURE 14 — 30 MC EQUIVALENT CIRCUIT

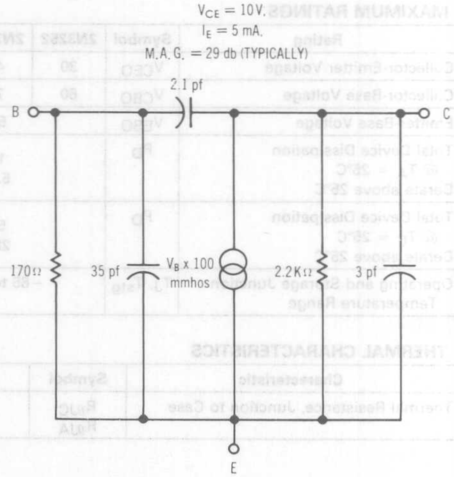


FIGURE 15 — JUNCTION CAPACITANCE

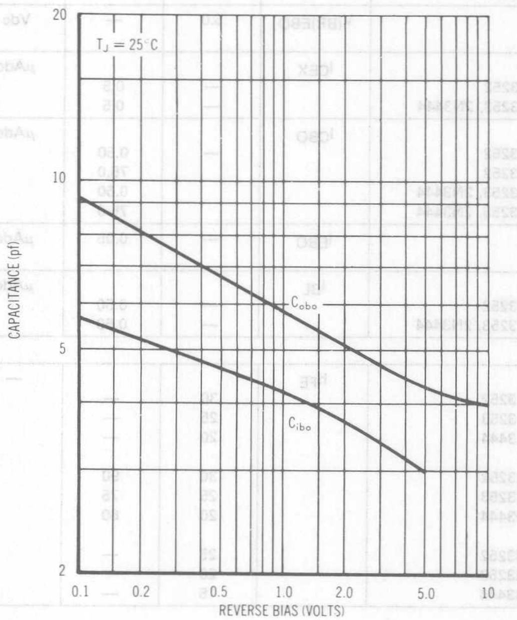
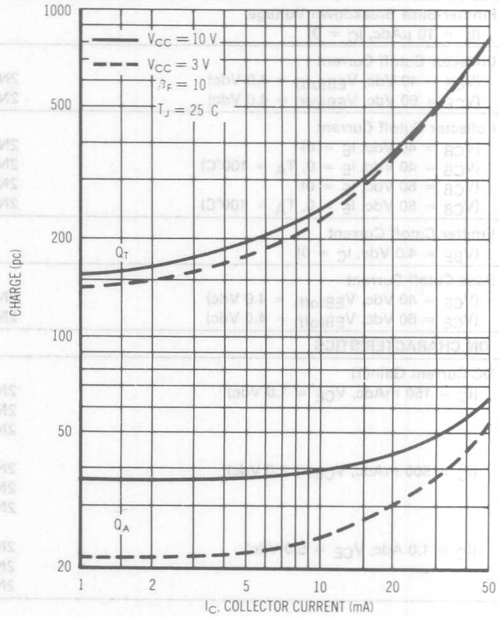


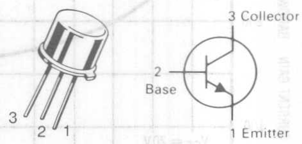
FIGURE 16 — CHARGE DATA



4

2N3252
2N3253
2N3444

JAN, JTX AVAILABLE
2N3253, 2N3444
CASE 79-02, STYLE 1
TO-39 (TO-205AD)



SWITCHING TRANSISTORS
NPN SILICON

4

MAXIMUM RATINGS

Rating	Symbol	2N3252	2N3253	2N3444	Unit
Collector-Emitter Voltage	V_{CEO}	30	40	50	Vdc
Collector-Base Voltage	V_{CBO}	60	75	80	Vdc
Emitter-Base Voltage	V_{EBO}		5.0		Vdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D		1.0 5.71		Watts mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D		5.0 28.6		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$ $R_{\theta JA}$	35 0.175	°C/W °C/mW

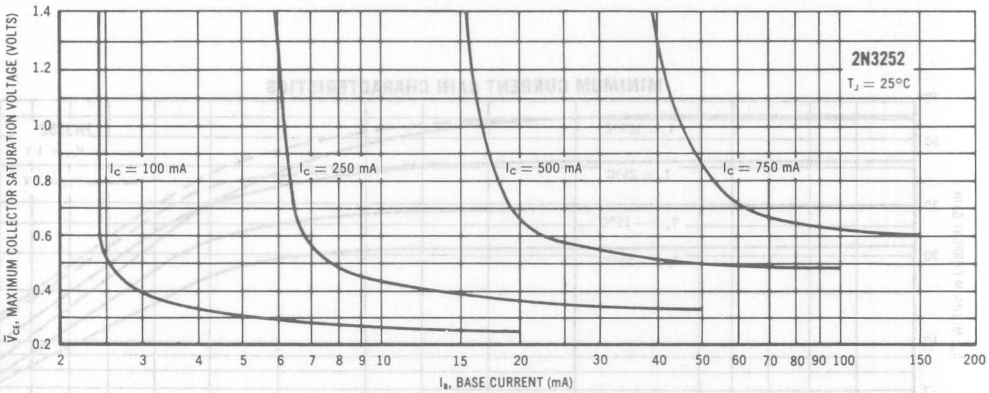
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, pulsed, I_B = 0)	2N3252 2N3253 2N3444	$V_{(BR)CEO}$	30 40 50	— — —	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	2N3252 2N3253 2N3444	$V_{(BR)CBO}$	60 75 80	— — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CE} = 40 Vdc, $V_{EB(off)}$ = 4.0 Vdc) (V_{CE} = 60 Vdc, $V_{EB(off)}$ = 4.0 Vdc)	2N3252 2N3253, 2N3444	I_{CEX}	— —	0.5 0.5	μAdc
Collector Cutoff Current (V_{CB} = 40 Vdc, I_E = 0) (V_{CB} = 40 Vdc, I_E = 0, T_A = 100°C) (V_{CB} = 60 Vdc, I_E = 0) (V_{CB} = 60 Vdc, I_E = 0, T_A = 100°C)	2N3252 2N3252 2N3253, 2N3444 2N3253, 2N3444	I_{CBO}	—	0.50 75.0 0.50 75.0	μAdc
Emitter Cutoff Current (V_{BE} = 4.0 Vdc, I_C = 0)		I_{EBO}	—	0.05	μAdc
Base Cutoff Current (V_{CE} = 40 Vdc, $V_{EB(off)}$ = 4.0 Vdc) (V_{CE} = 60 Vdc, $V_{EB(off)}$ = 4.0 Vdc)	2N3252 2N3253, 2N3444	I_{BL}	— —	0.50 0.50	μAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 150 mAdc, V_{CE} = 1.0 Vdc)	2N3252 2N3253 2N3444	h_{FE}	30 25 20	— — —	—
(I_C = 500 mAdc, V_{CE} = 1.0 Vdc)	2N3252 2N3253 2N3444		30 25 20	90 75 60	
(I_C = 1.0 Adc, V_{CE} = 5.0 Vdc)	2N3252 2N3253 2N3444		25 20 15	— — —	

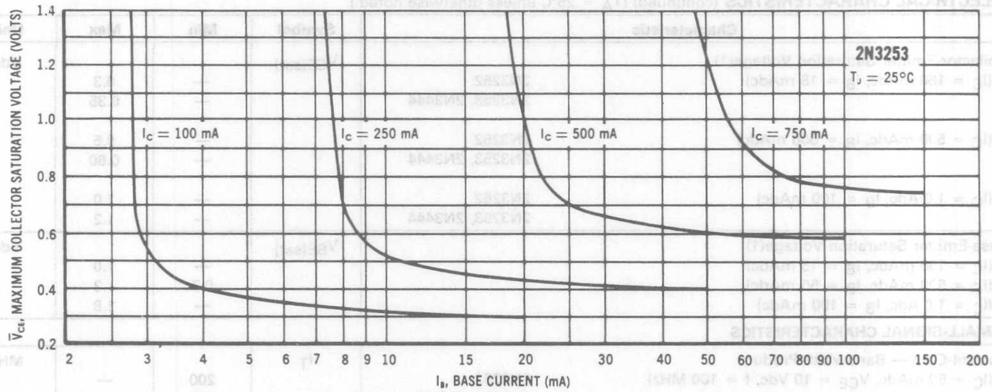
Characteristic		Symbol	Min	Max	Unit
Collector-Emitter Saturation Voltage(1)		$V_{CE(sat)}$			Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)	2N3252		—	0.3	
	2N3253, 2N3444		—	0.35	
(I_C = 500 mAdc, I_B = 500 mAdc)	2N3252		—	0.5	
	2N3253, 2N3444		—	0.60	
(I_C = 1.0 Adc, I_B = 100 mAdc)	2N3252		—	1.0	
	2N3253, 2N3444		—	1.2	
Base-Emitter Saturation Voltage(1)		$V_{BE(sat)}$			Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)			—	1.0	
(I_C = 500 mAdc, I_B = 50 mAdc)			0.7	1.3	
(I_C = 1.0 Adc, I_B = 100 mAdc)			—	1.8	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product		f_T			MHz
(I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	2N3252		200	—	
	2N3253, 2N3444		175	—	
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	12	pF
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	80	pF
SWITCHING CHARACTERISTICS					
Delay Time	I_C = 500 mAdc, I_{B1} = 50 mAdc	t_d	—	15	ns
Rise Time	V_{CC} = 30 V, V_{BE} = 2.0 V — 2N3252	t_r	—	30	ns
	2N3253, 2N3444		—	35	
Storage Time	I_C = 500 mAdc, I_{B1} = I_{B2} = 50 mAdc	t_s	—	40	ns
Fall Time	V_{CC} = 30 V	t_f	—	30	ns
Total Control Charge (I_C = 500 mAdc, I_{B1} = 50 mAdc, V_{CC} = 30 V)		Q_T		5.0	nC

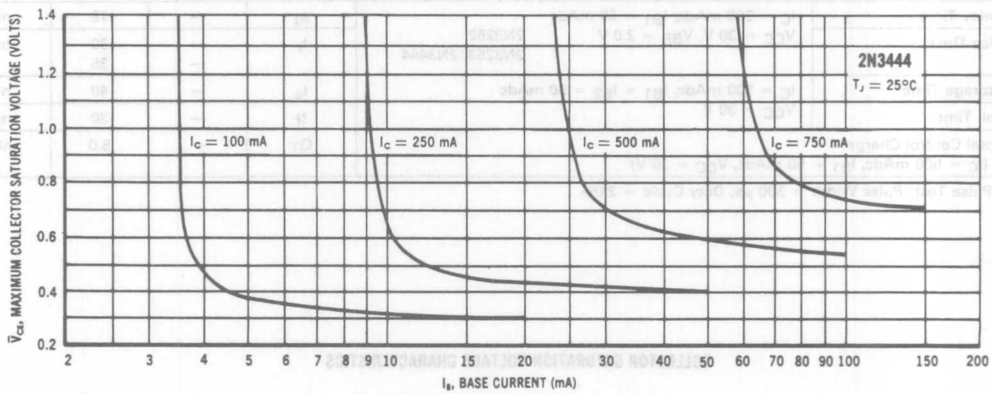
(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

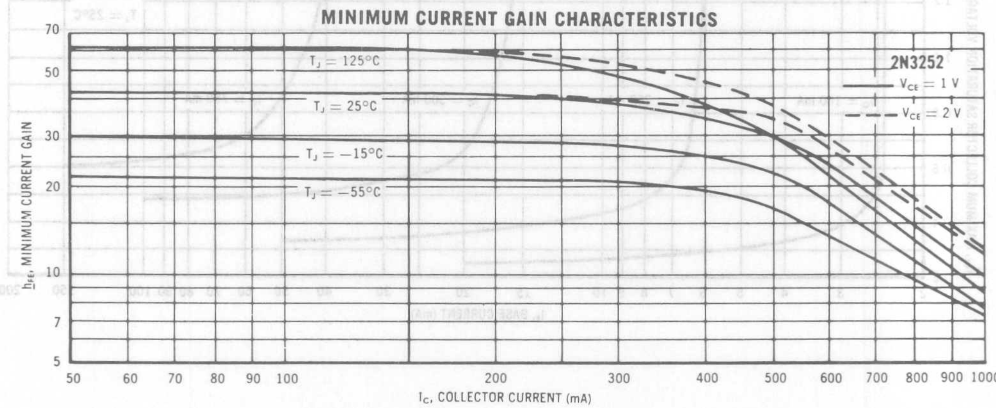
COLLECTOR SATURATION VOLTAGE CHARACTERISTICS

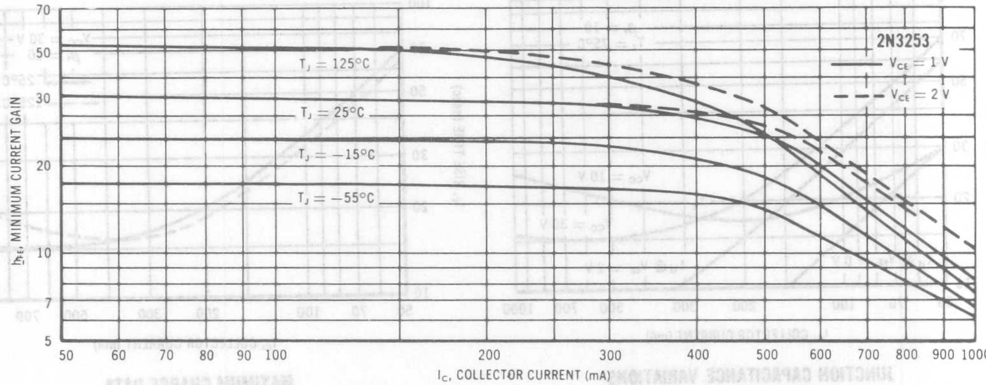


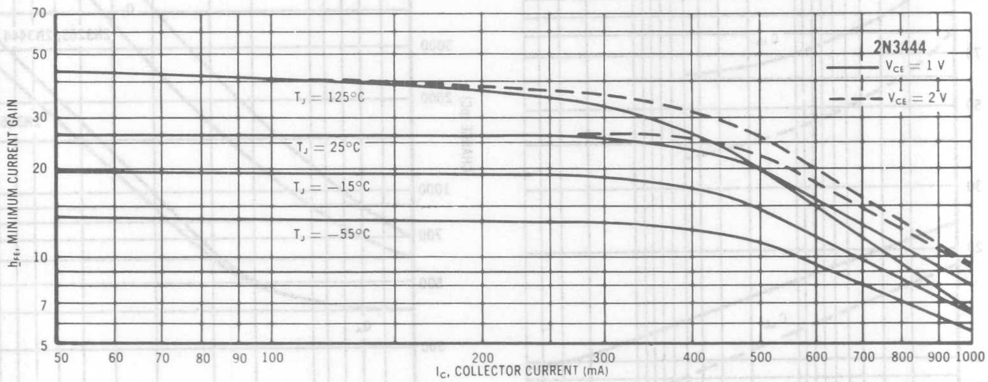
4

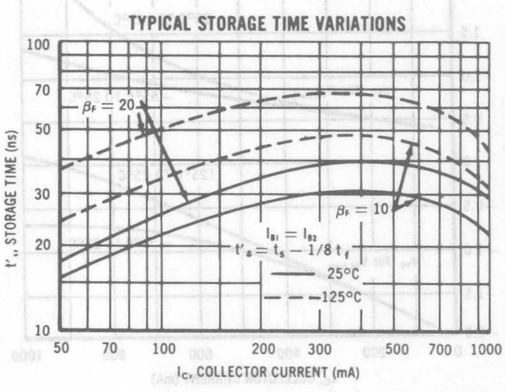

2N3253
$T_J = 25°C$
$I_C = 100$ mA
$I_C = 250$ mA
$I_C = 500$ mA
$I_C = 750$ mA
$\overline{V}_{CE}$, MAXIMUM COLLECTOR SATURATION VOLTAGE (VOLTS)
I_B, BASE CURRENT (mA)

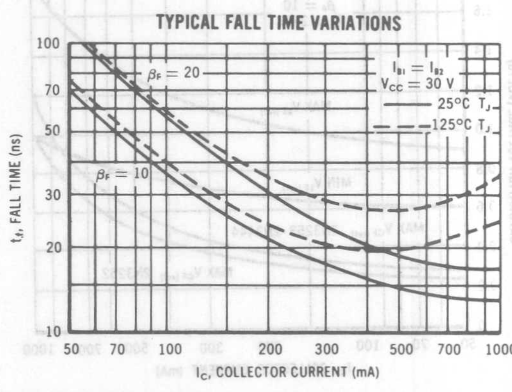

2N3444
$T_J = 25°C$
$I_C = 100$ mA
$I_C = 250$ mA
$I_C = 500$ mA
$I_C = 750$ mA
$\overline{V}_{CE}$, MAXIMUM COLLECTOR SATURATION VOLTAGE (VOLTS)
I_B, BASE CURRENT (mA)


MINIMUM CURRENT GAIN CHARACTERISTICS
2N3252
$V_{CE} = 1$ V
$V_{CE} = 2$ V
$T_J = 125°C$
$T_J = 25°C$
$T_J = -15°C$
$T_J = -55°C$
h_{FE}, MINIMUM CURRENT GAIN
I_C, COLLECTOR CURRENT (mA)


2N3253
V_{CE} = 1 V
V_{CE} = 2 V
T_J = 125°C
T_J = 25°C
T_J = −15°C
T_J = −55°C
h_{FE}, MINIMUM CURRENT GAIN
I_C, COLLECTOR CURRENT (mA)

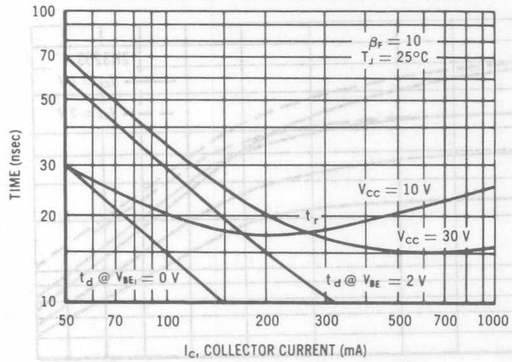

2N3444
V_{CE} = 1 V
V_{CE} = 2 V
T_J = 125°C
T_J = 25°C
T_J = −15°C
T_J = −55°C
h_{FE}, MINIMUM CURRENT GAIN
I_C, COLLECTOR CURRENT (mA)


TYPICAL STORAGE TIME VARIATIONS
β_F = 20
β_F = 10
$I_{B1} = I_{B2}$
$t'_s = t_s - 1/8\ t_f$
25°C
125°C
t'_s, STORAGE TIME (ns)
I_C, COLLECTOR CURRENT (mA)

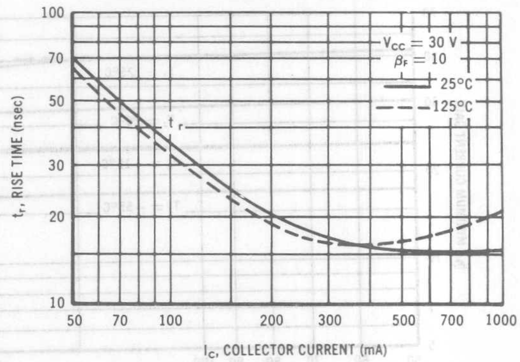

TYPICAL FALL TIME VARIATIONS
β_F = 20
β_F = 10
$I_{B1} = I_{B2}$
V_{CC} = 30 V
25°C T_J
125°C T_J
t_f, FALL TIME (ns)
I_C, COLLECTOR CURRENT (mA)

4

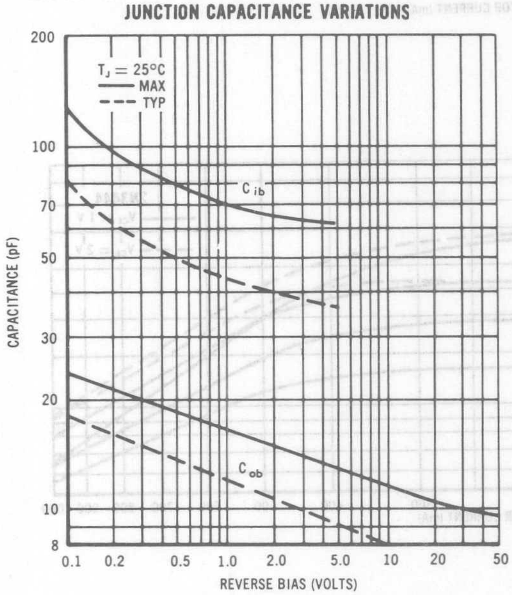
TYPICAL TURN-ON TIME VARIATIONS WITH VOLTAGE



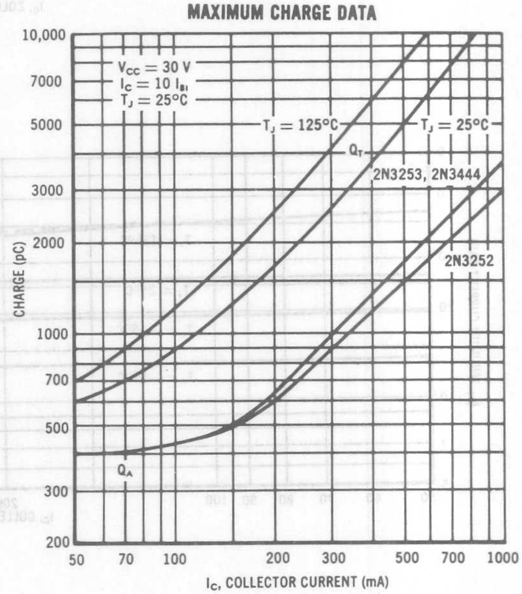
TYPICAL RISE TIME VARIATIONS WITH TEMPERATURE



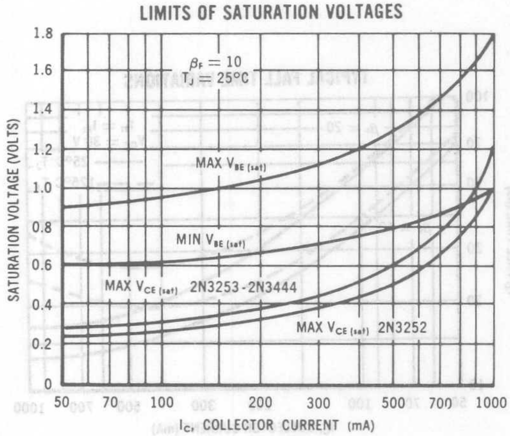
JUNCTION CAPACITANCE VARIATIONS



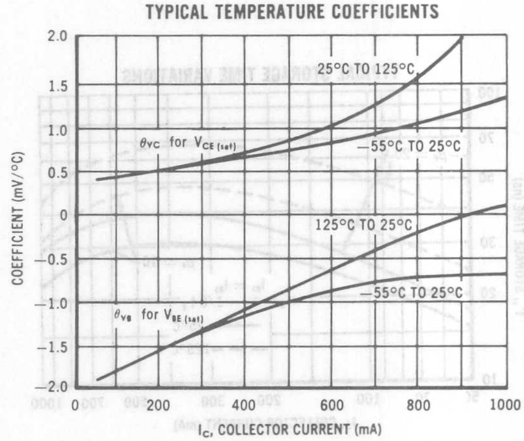
MAXIMUM CHARGE DATA



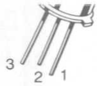
LIMITS OF SATURATION VOLTAGES



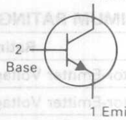
TYPICAL TEMPERATURE COEFFICIENTS



CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR



2N3302

CASE 22-03, STYLE 1
TO-18 (TO-206AA)

GENERAL PURPOSE TRANSISTOR

NPN SILICON

4

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage (Applicable 0 to 10 mAdc)	V_{CEO}	30		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
		2N3300	2N3302	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.8 4.56	0.36 2.06	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	3.0 17.2	1.8 10.3	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

Refer to 2N2218 for graphs.

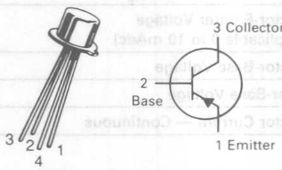
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage(1) (I_C = 10 mAdc, I_B = 0)	$V_{CEO(sus)}$	30		Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0		Vdc
Collector Cutoff Current (V_{CE} = 50 Vdc, V_{BE} = 0) (V_{CE} = 50 Vdc, V_{BE} = 0, T_A = 150°C)	I_{CES}	— —	0.01 10	μAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)	I_{EBO}		10	nAdc
Base Current (V_{CE} = 50 Vdc, V_{BE} = 0)	I_B	—	10	nAdc
ON CHARACTERISTICS				
DC Current Gain	h_{FE}			
(I_C = 0.1 mAdc, V_{CE} = 10 Vdc) 2N3300, 2N3302		35	—	
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc) 2N3300, 2N3302		50	—	
(I_C = 10 mAdc, V_{CE} = 10 Vdc)(1) 2N3300, 2N3302		75	—	
(I_C = 150 mAdc, V_{CE} = 1.0 Vdc)(1) 2N3300, 2N3302		50	—	
(I_C = 150 mAdc, V_{CE} = 10 Vdc)(1) 2N3300, 2N3302		100	300	
(I_C = 500 mAdc, V_{CE} = 10 Vdc)(1) 2N3300, 2N3302		50	—	
Collector-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 300 mAdc, I_B = 30 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)	$V_{CE(sat)}$	— — —	0.22 0.45 0.6	Vdc
Base-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 300 mAdc, I_B = 30 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)	$V_{BE(sat)}$	— — —	1.1 1.3 1.5	Vdc
Base Emitter Voltage (I_C = 150 mA, V_{CE} = 10 V)	$V_{BE(on)}$		1.1 V	Max
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	250		MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 140 kHz)	C_{obo}	—	8.0	pF
Input Capacitance (V_{BE} = 2.0 Vdc, I_C = 0, f = 140 kHz)	C_{ibo}	—	20	pF
SWITCHING CHARACTERISTICS				
Turn-On Time (V_{CC} = 25 Vdc, I_C = 300 mAdc, I_{B1} = 30 mAdc)	t_{on}	—	60	ns
Turn-Off Time (V_{CC} = 25 Vdc, I_C = 300 mAdc, I_{B1} = I_{B2} = 30 mAdc)	t_{off}	—	150	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2N3307
2N3308

CASE 20-03, STYLE 10
TO-72 (TO-206AF)



GENERAL PURPOSE TRANSISTORS

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	2N3307	2N3308	Unit
Collector-Emitter Voltage	V_{CEO}	35	25	Vdc
Collector-Emitter Voltage	V_{CES}	40	30	Vdc
Collector-Base Voltage	V_{CBO}	40	30	Vdc
Emitter-Base Voltage	V_{EBO}	3.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	200 1.14		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	300 1.71		mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

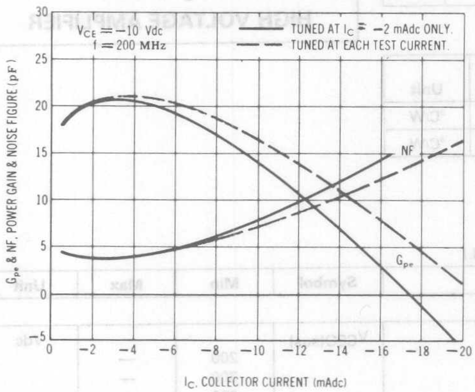
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 2.0$ mAdc, $I_B = 0$)	2N3307 2N3308	$V_{(BR)CEO}$	35 25	— —	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 10\ \mu$Adc, $V_{BE} = 0$)	2N3307 2N3308	$V_{(BR)CES}$	40 30	— —	Vdc
Collector-Base Breakdown Voltage(1) ($I_C = 10\ \mu$Adc, $I_E = 0$)	2N3307 2N3308	$V_{(BR)CBO}$	40 30	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	3.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc) ($V_{CB} = 15$ Vdc, T = 150°C)	 2N3307	I_{CBO}	 — —	 0.010 3.0	μAdc
ON CHARACTERISTICS					
DC Current Gain ($V_{CE} = 10$ Vdc, $I_C = 2.0$ mAdc)	2N3307 2N3308	h_{FE}	40 25	250 250	—
Collector-Emitter Saturation Voltage ($I_C = 3.0$ mAdc, $I_B = 0.6$ mAdc)		$V_{CE(sat)}$	—	0.4	Vdc
Base-Emitter Saturation Voltage ($I_C = 3.0$ mAdc, $I_B = 0.6$ mAdc		$V_{BE(sat)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($V_{CE} = 10$ Vdc, $I_C = 2.0$ mAdc, f = 100 MHz		f_T	300	1200	MHz
Maximum Frequency of Operation ($V_{CE} = 10$ Vdc, $I_C = 2.0$ mAdc)		f_{max}	Typical 2000		MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 0.1 MHz	2N3307 2N3308	C_{obo}	— —	1.3 1.6	pF
Small-Signal Current Gain ($V_{CE} = 10$ Vdc, $I_C = 2.0$ mAdc, f = 1 kHz)	2N3307 2N3308	h_{fe}	40 25	250 250	—
Collector Base Time Constant ($V_{CB} = 10$ Vdc, $I_C = 2.0$ mAdc, f = 31.8 MHz)	2N3307 2N3308	$rb'C_C$	2.0 2.0	15 20	ps

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

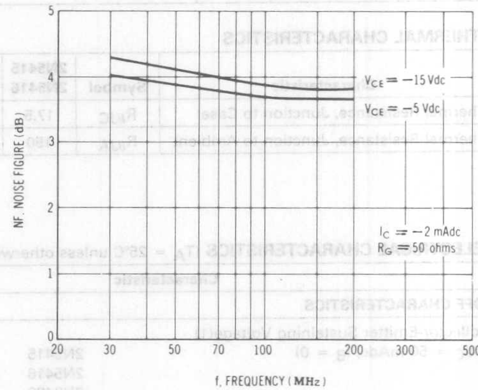
Characteristic		Symbol	Min	Max	Unit
Noise Figure (V_{CE} = 10 Vdc, I_C = 2.0 mAdc, f = 200 MHz)		NF			dB
	2N3307		—	4.5	
	2N3308		—	6.0	
SWITCHING CHARACTERISTICS					
Power Gain(2) (V_{CE} = 10 Vdc, I_C = 2.0 mAdc, f = 200 MHz)		G_e	17	—	dB
Power Gain (AGC)(2) (V_{CE} = 5.0 Vdc, I_C = 20 mAdc, f = 200 MHz)		G_e			dB
	2N3307		—	0	
	2N3308		—	—	

(1) C_{obo} is measured in guarded circuit such that the can capacitance is not included.
(2) AGC is obtained by increasing I_C. The circuit remains adjusted for V_{CE} = −10 Vdc, I_C = −2 mAdc operation.

COMMON EMITTER AVERAGE SMALL POWER GAIN & NOISE FIGURE versus COLLECTOR CURRENT



NOISE FIGURE versus FREQUENCY

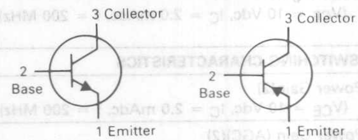


MAXIMUM RATINGS

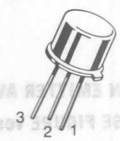
Rating	Symbol	PNP 2N5415	PNP 2N5416	NPN 2N3439	NPN 2N3440	Unit
Collector-Emitter Voltage	V_{CEO}	200	300	350	250	Vdc
Collector-Base Voltage	V_{CBO}	200	350	450	300	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	6.0	7.0	7.0	Vdc
Base Current	I_B	0.5				Adc
Collector Current — Continuous	I_C	1.0				Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	— —		1.0 5.7		Watts mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	10 57		5.0 28.6		Watts mW/°C
Total Device Dissipation @ T_A = 50°C Derate above 50°C	P_D	1.0 6.7		— —		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200				°C

NPN
2N3439
2N3440

PNP
2N5415
2N5416



JAN, JTX, JTXV AVAILABLE
CASE 79-02, STYLE 1
TO-39 (TO-205AD)



HIGH VOLTAGE AMPLIFIER

THERMAL CHARACTERISTICS

Characteristic	Symbol	2N5415 2N5416	2N3439 2N3440	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	17.5	35	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	150	175	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage(1) (I_C = 50 mAdc, I_B = 0)	2N5415 2N5416 2N3439 2N3440	$V_{CEO(sus)}$	200 300 350 250	— — — —	Vdc
*Collector Cutoff Current (V_{CE} = 300 Vdc, I_B = 0) (V_{CE} = 200 Vdc, I_B = 0)	2N3439 2N3440	I_{CEO}	— —	20 50	μAdc
*Collector Cutoff Current (V_{CE} = 450 Vdc, V_{BE} = 1.5 Vdc) (V_{CE} = 300 Vdc, V_{BE} = 1.5 Vdc)	2N3439 2N3440	I_{CEX}	— —	500 500	μAdc
Collector Cutoff Current (V_{CB} = 175 Vdc, I_E = 0) (V_{CB} = 280 Vdc, I_E = 0) (V_{CB} = 360 Vdc, I_E = 0) (V_{CB} = 250 Vdc, I_E = 0)	2N5415 2N5416 2N3439 2N3440	I_{CBO}	— — — —	50 50 20 20	μAdc
Emitter Cutoff Current (V_{EB} = 4.0 Vdc, I_C = 0) (V_{EB} = 6.0 Vdc, I_C = 0)	2N5415 2N5416, 2N3439, 2N3440	I_{EBO}	— —	20 20	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 2.0 mAdc, V_{CE} = 10 Vdc) *(I_C = 20 mAdc, V_{CE} = 10 Vdc) *(I_C = 50 mAdc, V_{CE} = 10 Vdc)	2N3439 2N3439, 2N3440 2N5415 2N5416	h_{FE}	30 40 30 30	— 160 150 120	—
Collector-Emitter Saturation Voltage (I_C = 50 mAdc, I_B = 4.0 mAdc)	2N3439, 2N3440	$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter Saturation Voltage (I_C = 50 mAdc, I_B = 4.0 mAdc)	2N3439, 2N3440	$V_{BE(sat)}$	—	1.3	Vdc

*Indicates Data in Addition to JEDEC Requirements.

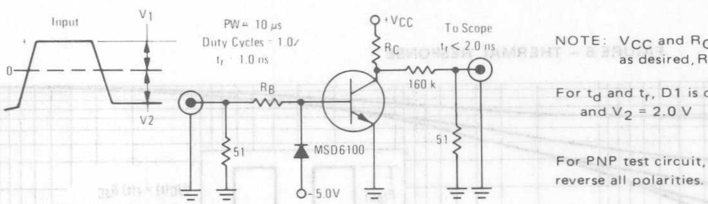
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 5.0 MHz)	2N3439, 2N3440	f_T	15	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	2N5415, 2N5416, 2N3439, 2N3440	C_{obo}	— —	15 10	pF
Input Capacitance (V_{EB} = 5.0 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	75	pF
Small-Signal Current Gain (I_C = 5.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz) (I_C = 10.0 mAdc, V_{CE} = 10 Vdc, f = 5.0 MHz)	2N5415, 2N5416	h_{fe}	25	—	—
Real Part of Input Impedance (V_{CE} = 10 Vdc, I_C = 5.0 mAdc, f = 1.0 MHz)		$Re(h_{ie})$	—	300	Ohms

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

CAUTION: The sustaining voltage *must not* be measured on a curve tracer. (See Fig. 15.)

FIGURE 1 – SWITCHING TIMES TEST CIRCUIT



NOTE: V_{CC} and R_C adjusted for $V_{CE(off)}$ = 150 V and I_C as desired, R_B chosen for desired I_{B1}, $V_1 \approx$ 10 V, $V_2 \approx$ 8.0 V

For t_d and t_r, D1 is disconnected and V_2 = 2.0 V

For PNP test circuit, reverse all polarities.

PNP 2N5415, 2N5416

NPN 2N3439, 2N3440

FIGURE 2 – TURN-ON TIME

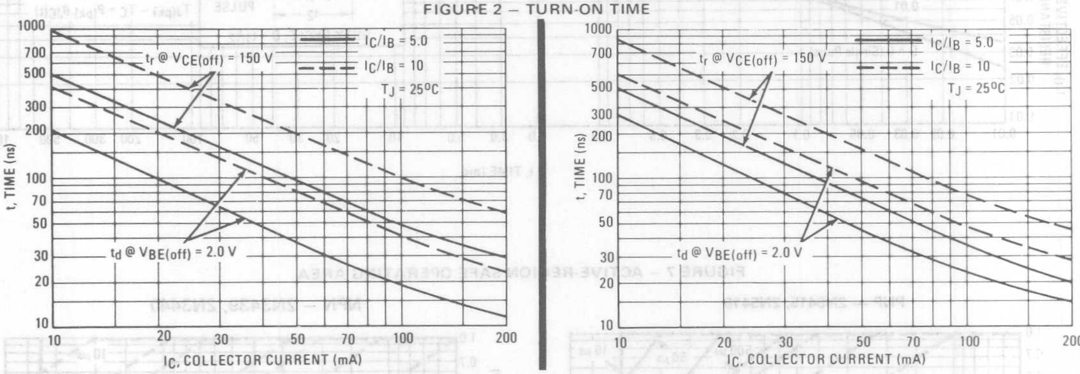


FIGURE 3 – TURN-OFF TIME

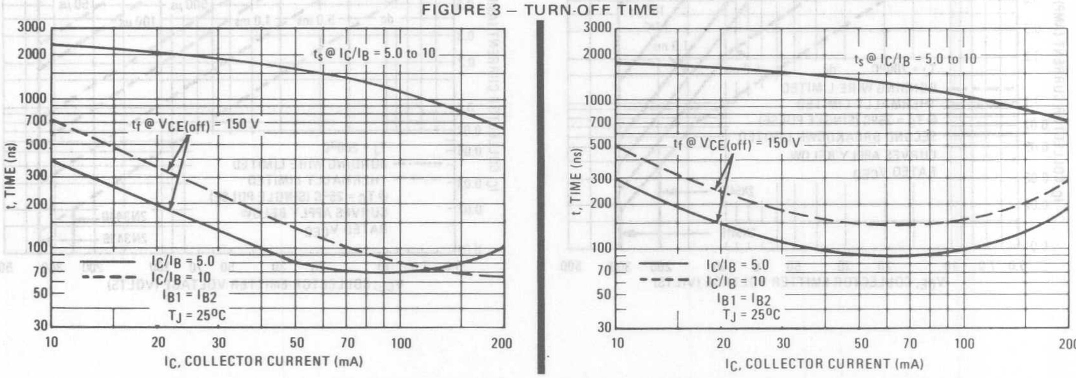


FIGURE 4 – CURRENT-GAIN – BANDWIDTH PRODUCT

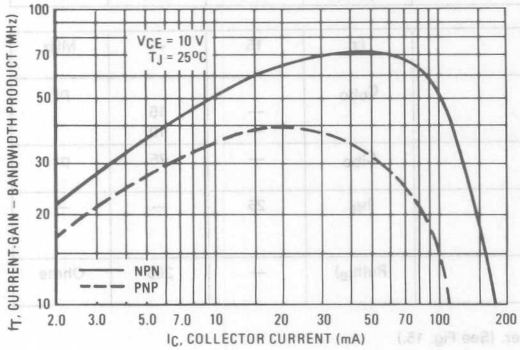


FIGURE 5 – CAPACITANCE

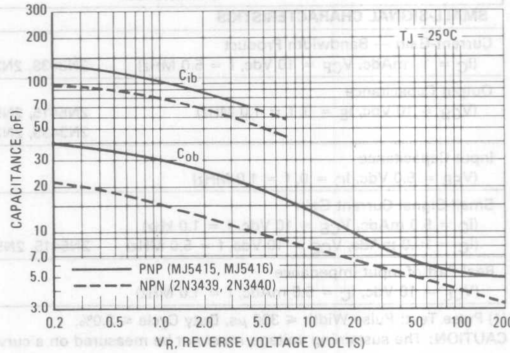


FIGURE 6 – THERMAL RESPONSE

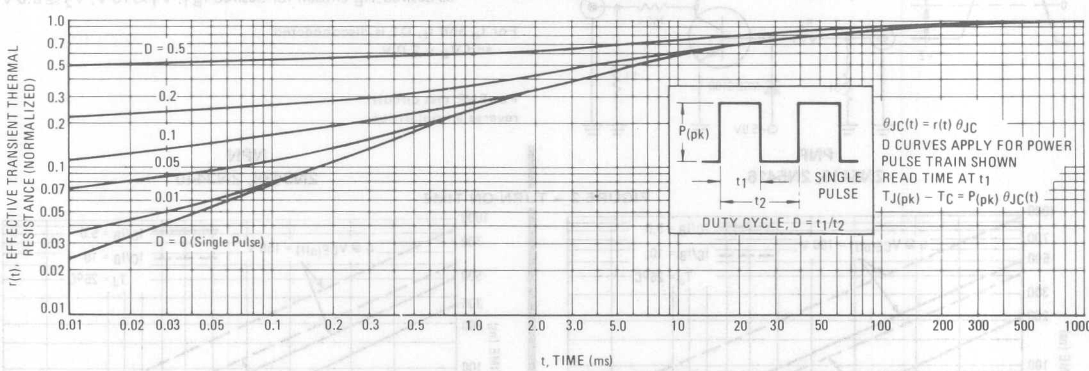


FIGURE 7 – ACTIVE-REGION SAFE OPERATING AREA

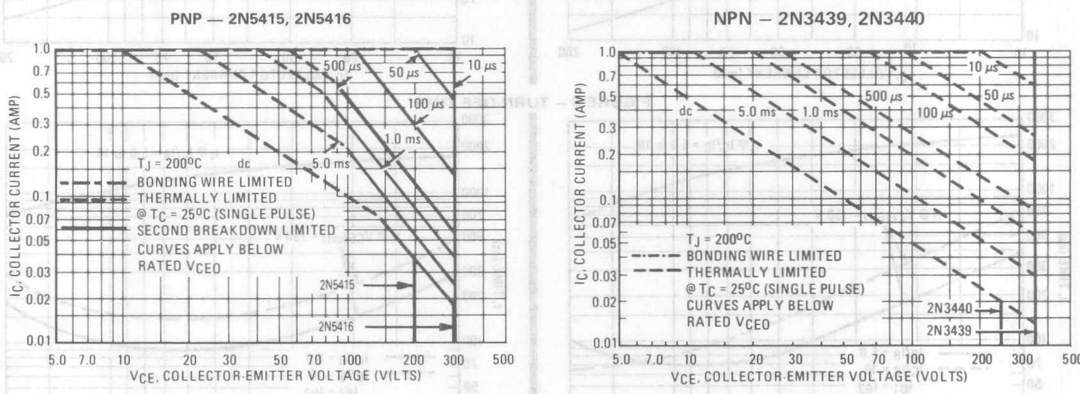
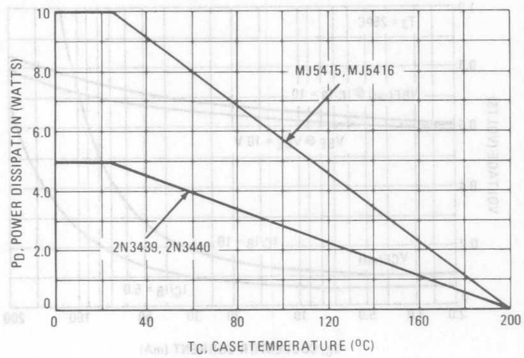


FIGURE 8 – POWER DERATING



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 7 is based on $T_{J(pk)} = 200^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 200^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 6. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. (See AN-415).

PNP
2N5415, 2N5416

NPN
2N3439 2N3440

FIGURE 9 – DC CURRENT GAIN

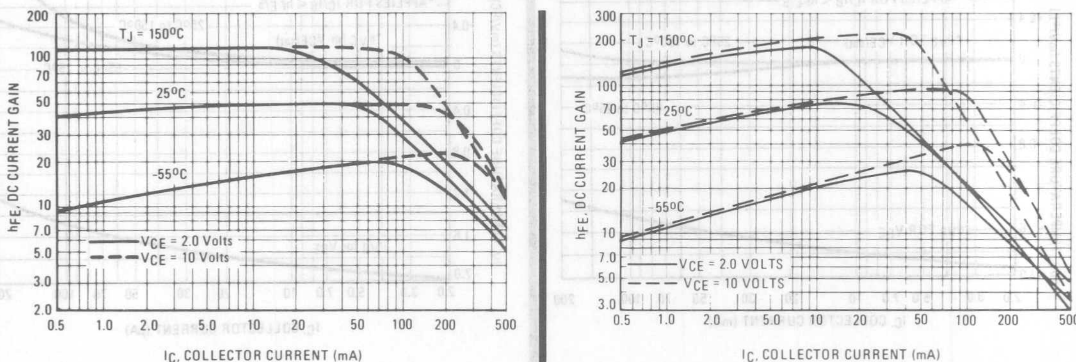
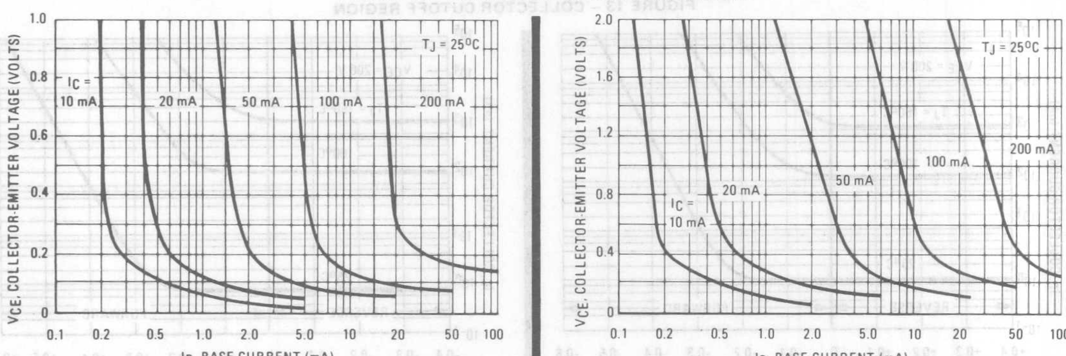
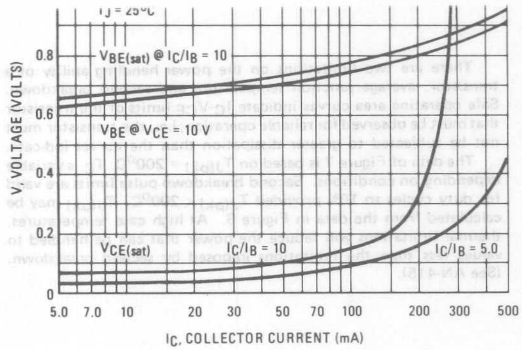


FIGURE 10 – COLLECTOR SATURATION REGION





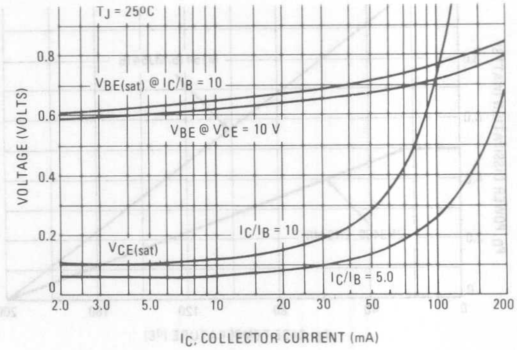
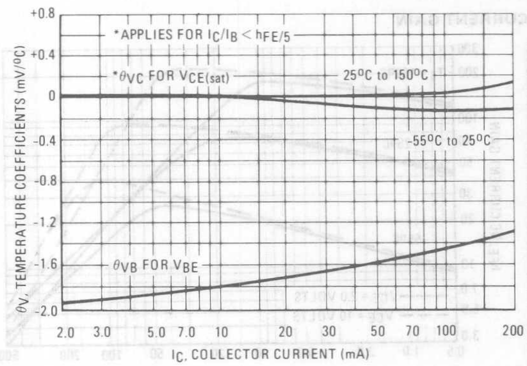


FIGURE 12 – TEMPERATURE COEFFICIENTS



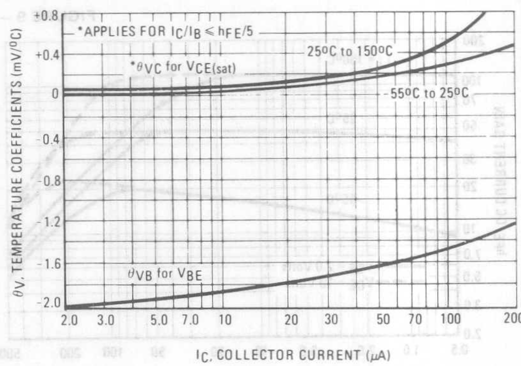
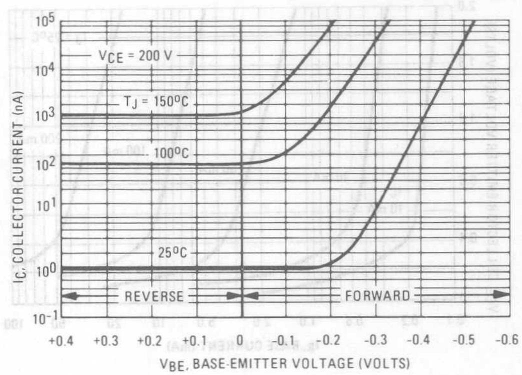
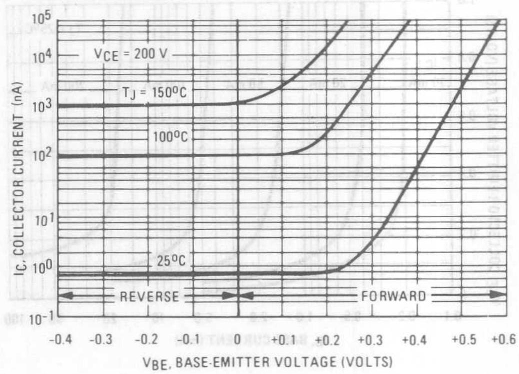
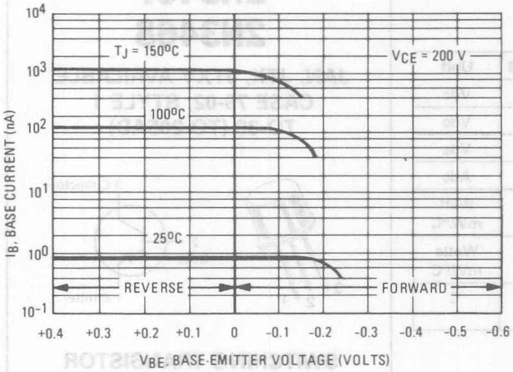
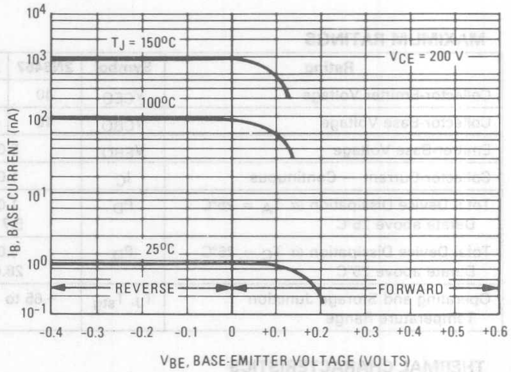


FIGURE 13 – COLLECTOR CUTOFF REGION



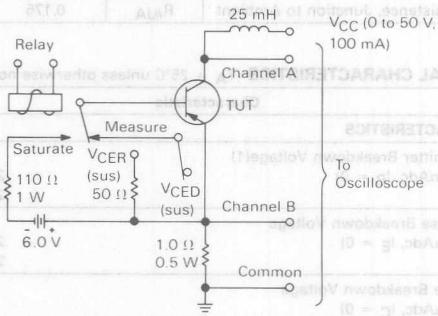






4

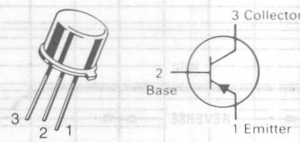
FIGURE 15 — CIRCUIT USED TO MEASURE SUSTAINING VOLTAGES



2N3444 For Specifications, See 2N3252 Data.

2N3467
2N3468

JAN, JTX, JTXV AVAILABLE
CASE 79-02, STYLE 1
TO-39 (TO-205AD)



SWITCHING TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	2N3467	2N3468	Unit
Collector-Emitter Voltage	V_{CEO}	40	50	Vdc
Collector-Base Voltage	V_{CBO}	40	50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	1.0		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 5.71		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5.0 28.6		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	0.175	°C/mW

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

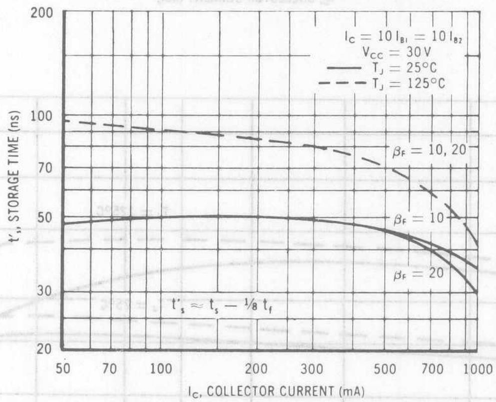
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	 2N3467 2N3468	$V_{(BR)CEO}$	 40 50	 — —	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	 2N3467 2N3468	$V_{(BR)CBO}$	 40 50	 — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Base Cutoff Current (V_{CE} = −30 Vdc, V_{BE} = 3.0 Vdc)		I_{BEV}	—	120	nAdc
Collector Cutoff Current (V_{CE} = −30 Vdc, V_{BE} = 3.0 Vdc)		I_{CEX}	—	100	nAdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0) (V_{CB} = 30 Vdc, I_E = 0, T_A = 100°C)		I_{CBO}	 — —	 0.10 15	μAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 150 mAdc, V_{CE} = 1.0 Vdc)	 2N3467 2N3468	h_{FE}	 40 25	 — —	—
(I_C = 500 mAdc, V_{CE} = 1.0 Vdc)	2N3467 2N3468		40 25	120 75	
(I_C = 1.0 Adc, V_{CE} = 5.0 Vdc)	2N3467 2N3468		40 20	— —	
Collector-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc)	 2N3467 2N3468	$V_{CE(sat)}$	 — —	 0.3 0.36	Vdc
(I_C = 500 mAdc, I_B = 50 mAdc)	2N3467 2N3468		— —	0.5 0.6	
(I_C = 1.0 Adc, I_B = 100 mAdc)	2N3467 2N3468		— —	1.0 1.2	
Base-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc) (I_C = 1.0 Adc, I_B = 100 mAdc)		$V_{BE(sat)}$	 — 0.8 —	 1.0 1.2 1.6	Vdc

ELECTRICAL CHARACTERISTICS (continued) ($T_A = 25°C$ unless otherwise noted.)

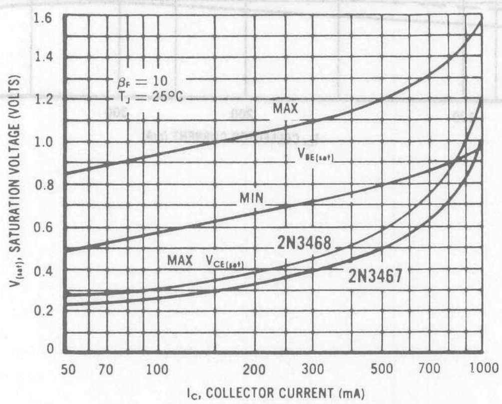
Characteristic		Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	2N3467	f_T	175	—	MHz
	2N3468		150	—	
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)		C_{obo}	—	25	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz)		C_{ibo}	—	100	pF
SWITCHING CHARACTERISTICS					
Delay Time	($I_C = 500$ mA, $I_{B1} = 50$ mA, $V_{BE} = 2.0$ V, $V_{CC} = 30$ V)	t_d	—	10	ns
Rise Time		t_r	—	30	ns
Storage Time	($I_C = 500$ mA, $I_{B1} = I_{B2} = 50$ mA, $V_{CC} = 30$ V)	t_s	—	60	ns
Fall Time		t_f	—	30	ns
Total Control Charge ($I_C = 500$ mA, $I_B = 50$ mA, $V_{CC} = 30$ V)		Q_T	—	6.0	nC

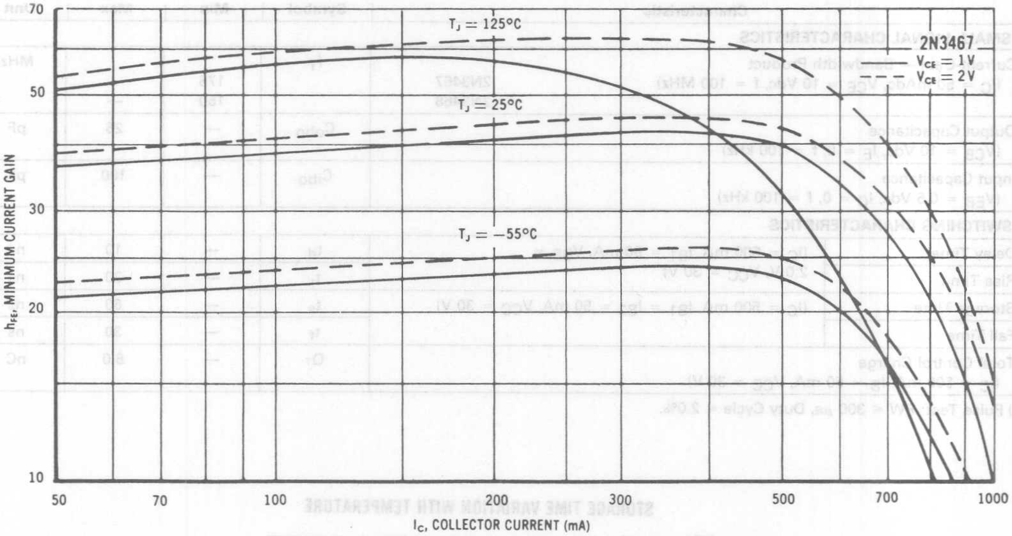
(1) Pulse Test: PW ≤ 300 μs, Duty Cycle ≤ 2.0%.

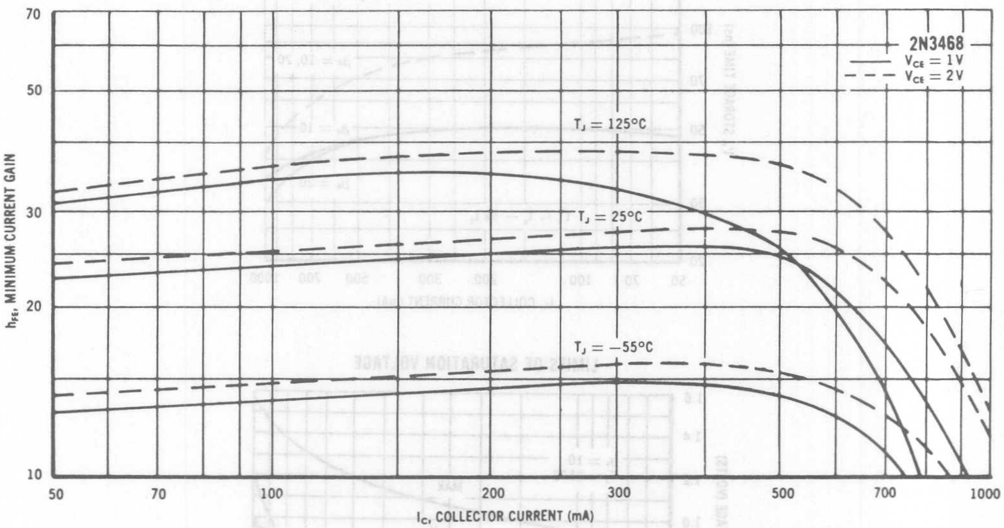
STORAGE TIME VARIATION WITH TEMPERATURE



LIMITS OF SATURATION VOLTAGE

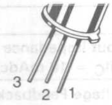


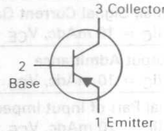

2N3467
V_{CE} = 1 V
V_{CE} = 2 V
T_J = 125°C
T_J = 25°C
T_J = −55°C
h_{FE}, MINIMUM CURRENT GAIN
I_C, COLLECTOR CURRENT (mA)


2N3468
V_{CE} = 1 V
V_{CE} = 2 V
T_J = 125°C
T_J = 25°C
T_J = −55°C
h_{FE}, MINIMUM CURRENT GAIN
I_C, COLLECTOR CURRENT (mA)

2N3494
2N3495

CASE 79-02, STYLE 1
TO-39 (TO-205AD)





2N3496
2N3497

CASE 22-03, STYLE 1
TO-18 (TO-206AA)

GENERAL PURPOSE TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	2N3494 2N3496	2N3495 2N3497	Unit
Collector-Emitter Voltage	V_{CEO}	80	120	Vdc
Collector-Base Voltage	V_{CBO}	80	120	Vdc
Emitter-Base Voltage	V_{EBO}	4.5		Vdc
Collector Current — Continuous	I_C	100		mAdc
		2N3494 2N3495	**2N3496 2N3497**	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	600 3.43	400 2.28	mW mW/°C
Total Device Dissipation @ T_C = 25°C* Derate above 25°C	P_D	3.0 17.2	1.2 6.85	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

*Indicates Data in addition to JEDEC Requirements.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	2N3494, 2N3496 2N3495, 2N3497	$V_{(BR)CEO}$	80 120	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	2N3494, 2N3496 2N3495, 2N3497	$V_{(BR)CBO}$	80 120	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	4.5	—	Vdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0) (V_{CB} = 90 Vdc, I_E = 0)	2N3494, 2N3496 2N3495, 2N3497	I_{CBO}	— —	100 100	nAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)		I_{EBO}	—	25	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 100 μAdc, V_{CE} = 10 Vdc) (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc) (I_C = 50 mAdc, V_{CE} = 10 Vdc) (I_C = 100 mAdc, V_{CE} = 10 Vdc)	2N3494, 2N3496	h_{FE}	35 40 40 40 35	— — — — —	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	2N3494, 2N3496 2N3495, 2N3497	$V_{CE(sat)}$	— —	0.3 0.35	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{BE(sat)}$	0.6	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	2N3494, 2N3496 2N3495, 2N3497	f_T	200 150	— —	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	2N3494, 2N3496 2N3495, 2N3497	C_{obo}	— —	7.0 6.0	pF
Input Capacitance (V_{BE} = 2.0 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	30	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Input Impedance (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{ie}	0.1	1.2	k ohms
Voltage Feedback Ratio (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{re}	—	2.0	X 10^{-4}
Small-Signal Current Gain (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{fe}	40	300	—
Output Admittance (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{oe}	—	300	μmhos
Real Part of Input Impedance (I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 300 MHz)	$Re(h_{ie})$	—	30	Ohms
SWITCHING CHARACTERISTICS				
Turn-On Time (V_{CC} = 30 Vdc, I_C = 10 mAdc, I_{B1} = 1.0 mAdc)	t_{on}	—	300	ns
Turn-Off Time (V_{CC} = 30 Vdc, I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)	t_{off}	—	1000	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 2.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

FIGURE 1 — TURN-ON TIME TEST CIRCUIT

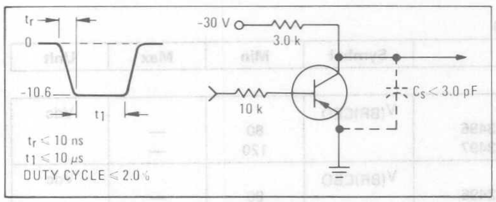


FIGURE 2 — TURN-OFF TIME TEST CIRCUIT

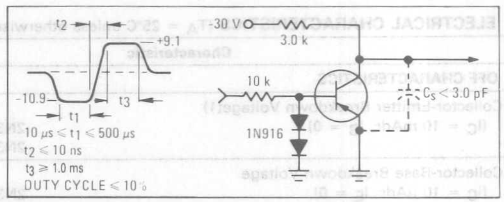


FIGURE 3 — V_{CE} (sat) versus I_C

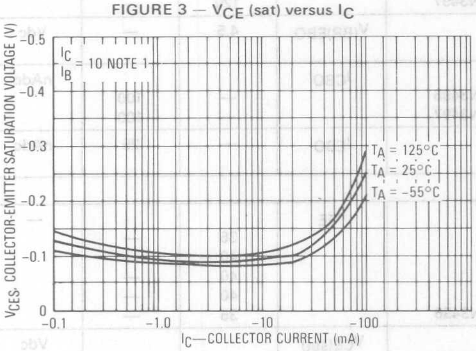


FIGURE 4 — I_{CBO} versus T_A

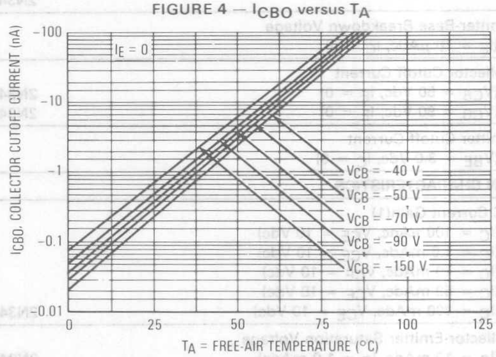


FIGURE 5 — h_{FE} versus I_C

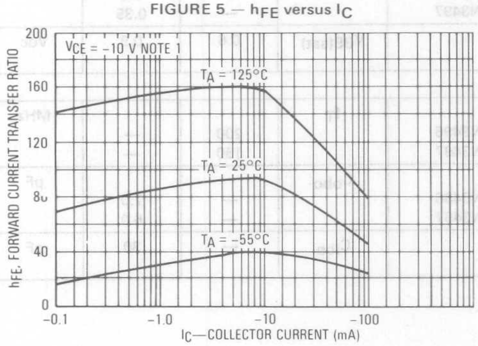


FIGURE 6 — V_{BE} versus I_C

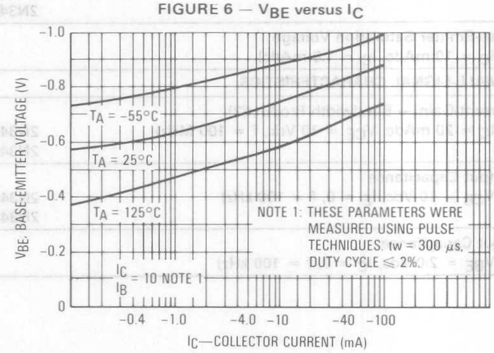


FIGURE 7 — f_T versus I_C

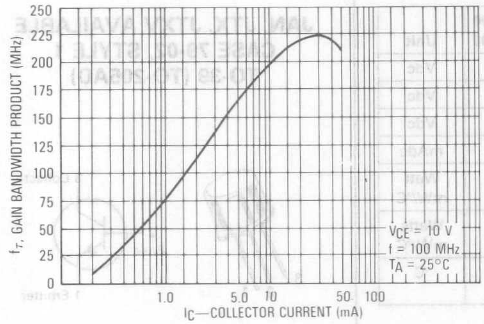


FIGURE 8 — C_{OBO} versus V_{CB}

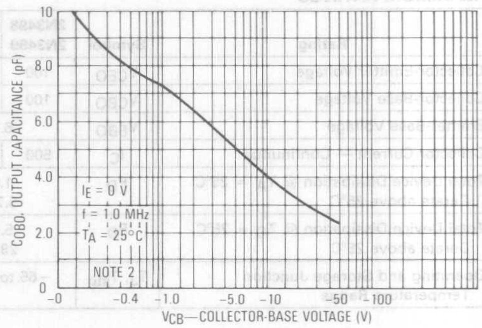
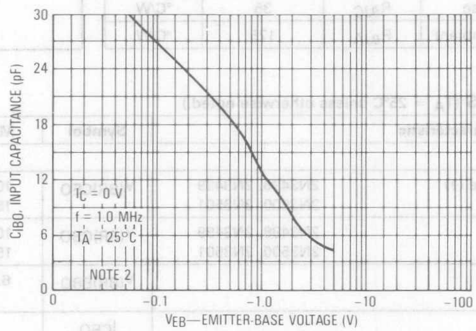


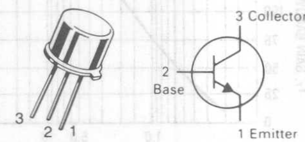
FIGURE 9 — C_{IBO} versus V_{EB}



NOTE 2: CAPACITANCE MEASURE MADE WITH TO-18 PACKAGE.

2N3498 thru 2N3501

JAN, JTX, JTXV AVAILABLE
CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

4

MAXIMUM RATINGS

Rating	Symbol	2N3498 2N3499	2N3500 2N3501	Unit
Collector-Emitter Voltage	V_{CEO}	100	150	Vdc
Collector-Base Voltage	V_{CBO}	100	150	Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	500	300	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 5.71		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5.0 28.6		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	175	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (1) ($I_C = 10$ mAdc, $I_B = 0$)	2N3498, 2N3499 2N3500, 2N3501	$V_{(BR)CEO}$	100 150	— —	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	2N3498, 2N3499 2N3500, 2N3501	$V_{(BR)CBO}$	100 150	— —	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	6.0	— —	— —	Vdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$) ($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = 150°C$) ($V_{CB} = 75$ Vdc, $I_E = 0$) ($V_{CB} = 75$ Vdc, $I_E = 0$, $T_A = 150°C$)	 2N3498, 2N3499 2N3500, 2N3501	I_{CBO}	 — — — —	 — — — —	 0.050 50 0.050 50	μAdc
Emitter Cutoff Current ($V_{BE(off)} = 4.0$ Vdc, $I_C = 0$)		I_{EBO}	—	—	25	nAdc
ON CHARACTERISTICS						
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 10$ Vdc)	 2N3498, 2N3500 2N3499, 2N3501	h_{FE}	 20 35	 — —	 — —	—
($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc)	2N3498, 2N3500 2N3499, 2N3501		25 50	— —	— —	
($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc)	2N3498, 2N3500 2N3499, 2N3501		35 75	— —	— —	
($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)	2N3498, 2N3500 2N3499, 2N3501		40 100	— —	120 300	
($I_C = 300$ mAdc, $V_{CE} = 10$ Vdc)	2N3500 2N3501		15 20	— —	— —	
($I_C = 500$ mAdc, $V_{CE} = 10$ Vdc)	2N3498 2N3499		15 20	— —	— —	
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc) ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 300$ mAdc, $I_B = 30$ mAdc)	 All Types All Types 2N3500, 2N3501 2N3498, 2N3499	$V_{CE(sat)}$	 — — — —	 — — — —	 0.2 0.25 0.4 0.6	Vdc

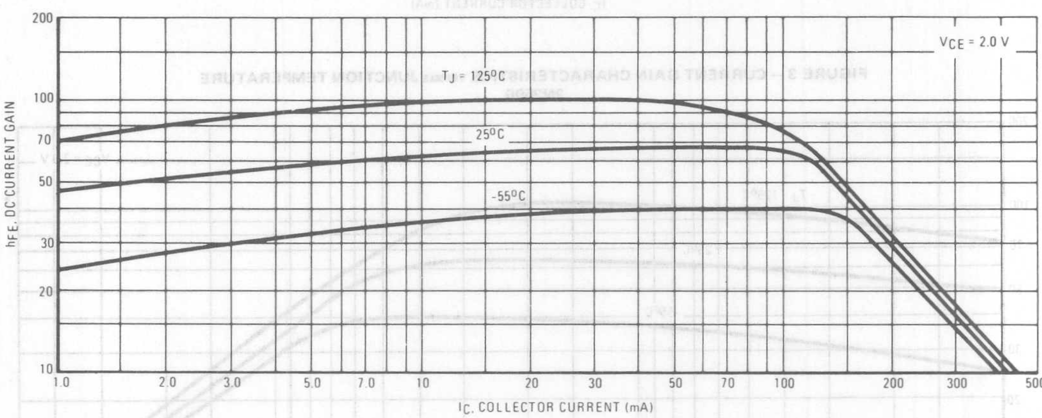
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
Base-Emitter Saturation Voltage		$V_{BE(sat)}$				Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)	All Types		—	—	0.8	
(I_C = 50 mAdc, I_B = 5.0 mAdc)	All Types		—	—	0.9	
(I_C = 150 mAdc, I_B = 15 mAdc)	2N3500, 2N3501		—	—	1.2	
(I_C = 300 mAdc, I_B = 30 mAdc)	2N3498, 2N3499		—	—	1.4	
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product(2) (V_{CE} = 20 Vdc, I_C = 20 mAdc, f = 100 MHz)		f_T	150	—	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	2N3498, 2N3499 2N3500, 2N3501	C_{obo}	— —	— —	10 8.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	—	80	pF
Input Impedance (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3498, 2N3500 2N3499, 2N3501	h_{ie}	0.2 0.25	— —	1.0 1.25	k ohms
Voltage Feedback Ratio (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3498, 2N3500 2N3499, 2N3501	h_{re}	— —	— —	2.5 4.0	X 10^{-4}
Small-Signal Current Gain (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3498, 2N3500 2N3499, 2N3501	h_{fe}	50 75	— —	300 375	—
Output Admittance (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3498, 2N3500 2N3499, 2N3501	h_{oe}	— —	— —	100 200	μmhos
SWITCHING CHARACTERISTICS						
Delay Time (I_C = 150 mAdc, I_{B1} = 15 mAdc, V_{CC} = 100 Vdc, $V_{BE(off)}$ = 2.0 Vdc)		t_d	—	20	—	ns
Rise Time (I_C = 150 mAdc, I_{B1} = 15 mAdc, V_{CC} = 100 Vdc, $V_{BE(off)}$ = 2.0 Vdc)		t_r	—	35	—	ns
Storage Time (I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc, V_{CC} = 100 Vdc)		t_s	—	800	—	ns
Fall Time (I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc, V_{CC} = 100 Vdc)		t_f	—	80	—	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) $f_T = |h_{fe}| \cdot f_{test}$.

4

FIGURE 1 — CURRENT GAIN CHARACTERISTICS versus JUNCTION TEMPERATURE
2N3498



2N3499

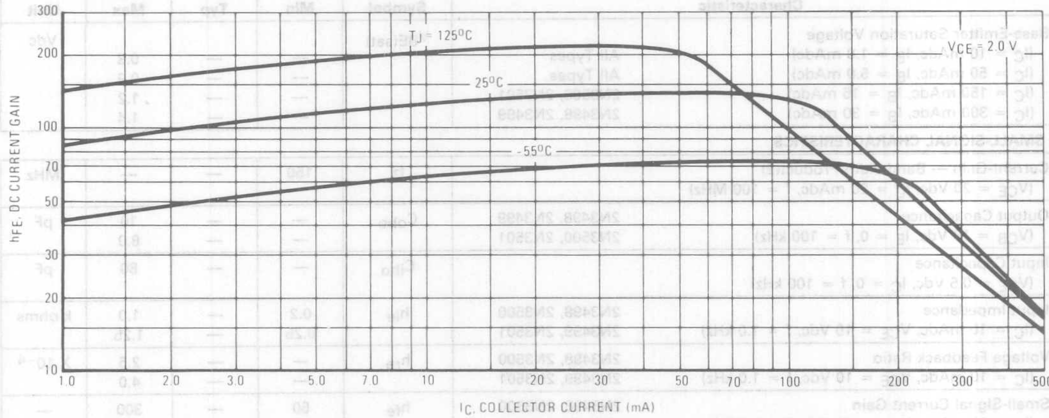


FIGURE 2 – CURRENT GAIN CHARACTERISTICS versus COLLECTOR-EMITTER VOLTAGE

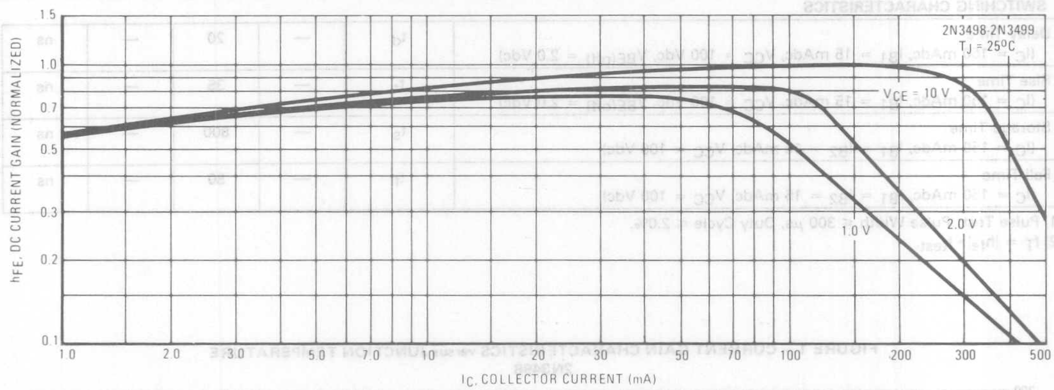


FIGURE 3 – CURRENT GAIN CHARACTERISTICS versus JUNCTION TEMPERATURE
2N3500

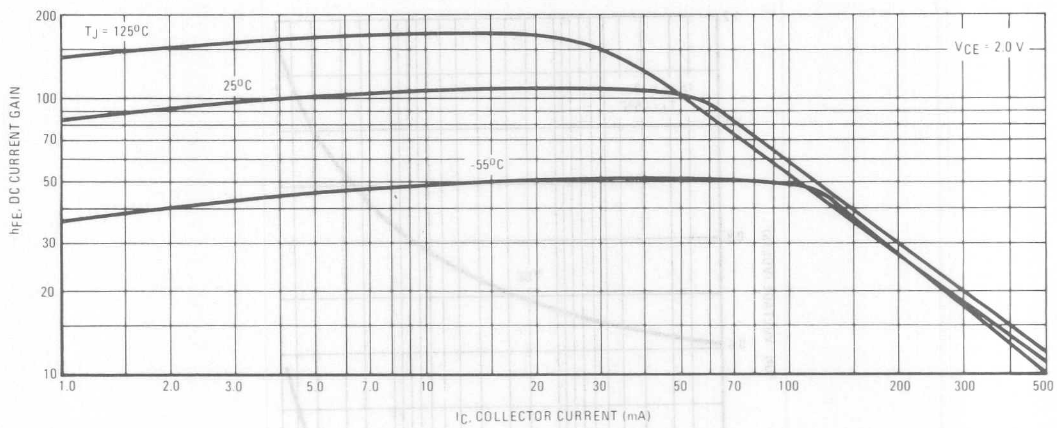


FIGURE 4 – CURRENT GAIN CHARACTERISTICS versus COLLECTOR-EMITTER VOLTAGE

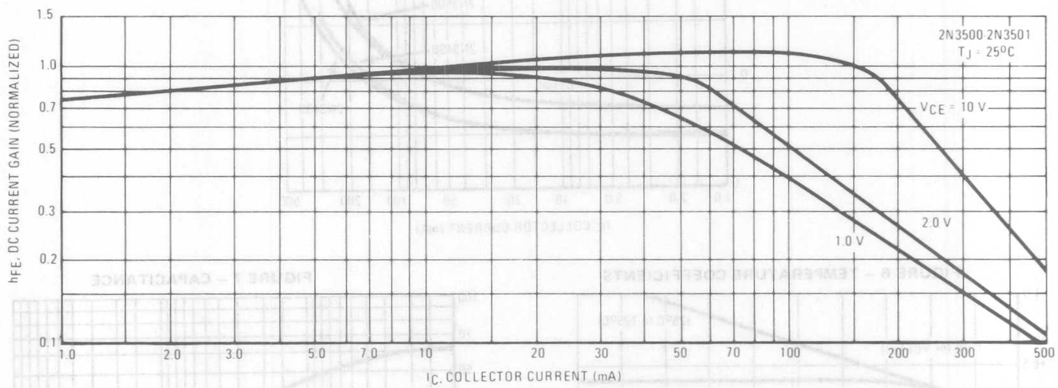


FIGURE 5 — "ON" VOLTAGES

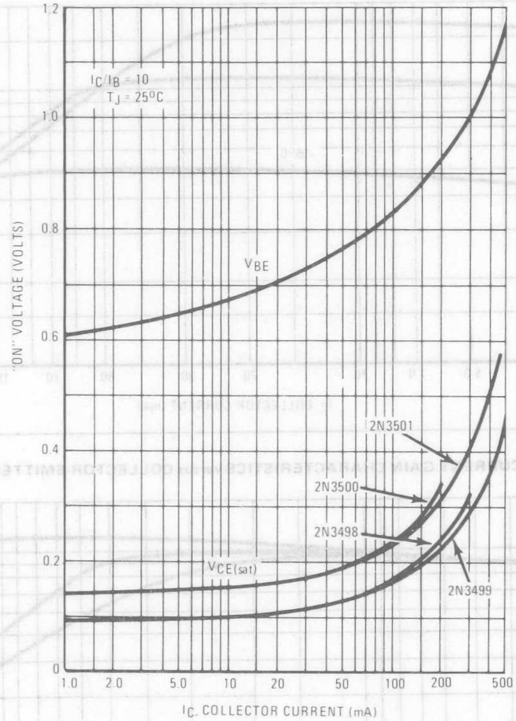


FIGURE 6 — TEMPERATURE COEFFICIENTS

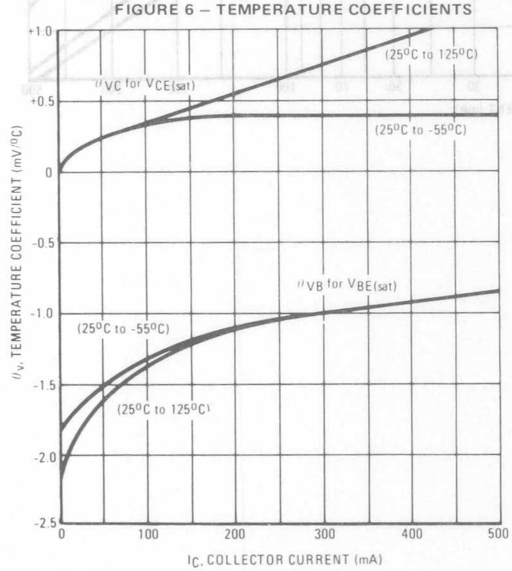
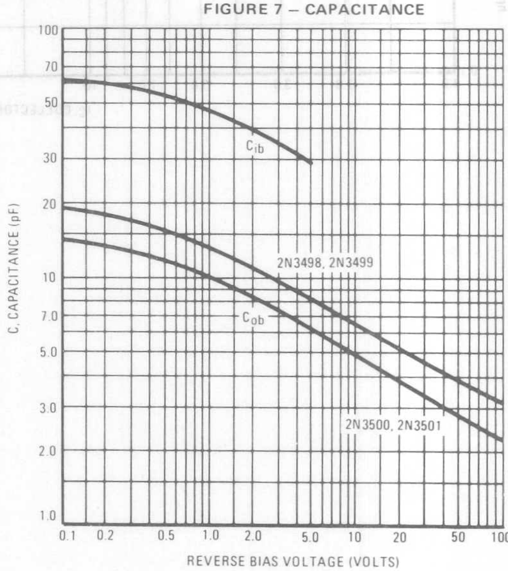


FIGURE 7 — CAPACITANCE



AUDIO SMALL-SIGNAL h PARAMETER CHARACTERISTICS

(V_{CE} = 10 Vdc, T_A = 25°C, f = 1.0 kHz)

FIGURE 8 – CURRENT GAIN

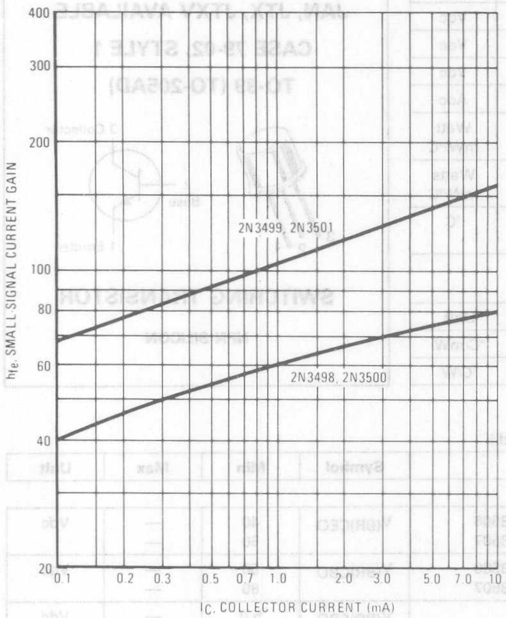


FIGURE 9 – OUTPUT IMPEDANCE

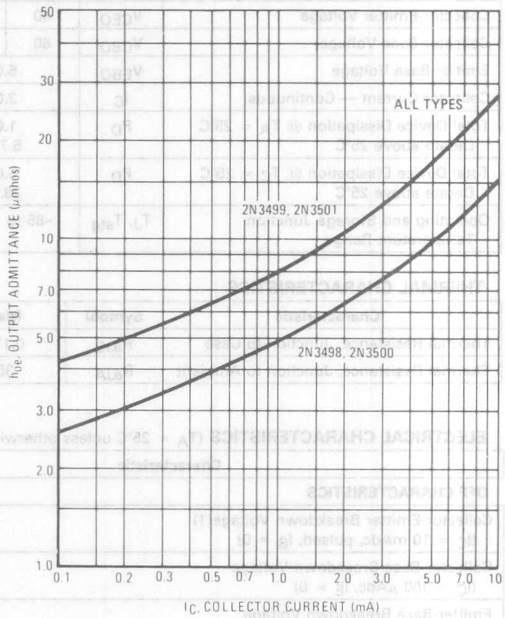


FIGURE 10 – INPUT IMPEDANCE

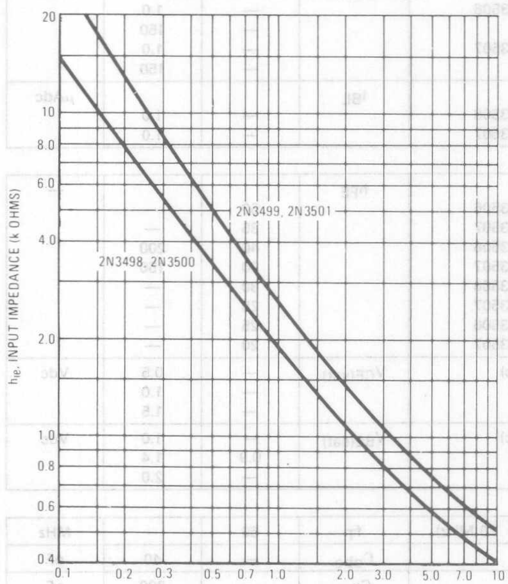
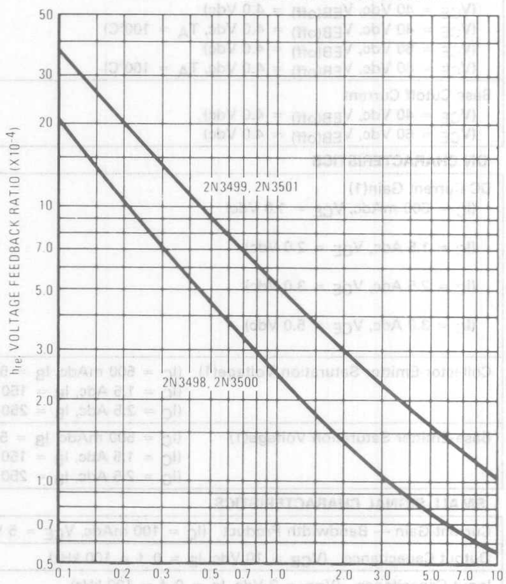


FIGURE 11 – VOLTAGE FEEDBACK RATIO

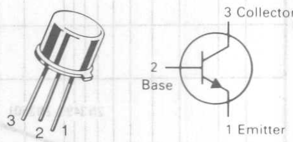


4

2N3506
2N3507

JAN, JTX, JTXV AVAILABLE

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



SWITCHING TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	2N3506	2N3507	Unit
Collector-Emitter Voltage	V_{CEO}	40	50	Vdc
Collector-Base Voltage	V_{CBO}	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	3.0		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 5.71		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5.0 28.6		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.175	°C/mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	35	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

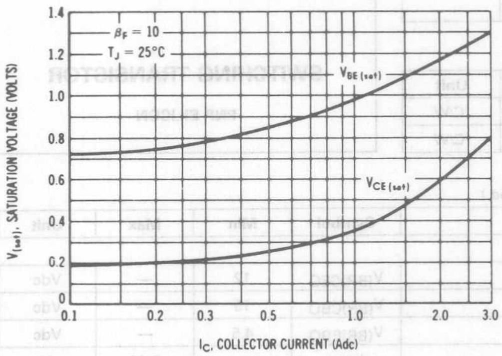
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, pulsed, $I_B = 0$)	2N3506 2N3507	$V_{(BR)CEO}$	40 50	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	2N3506 2N3507	$V_{(BR)CBO}$	60 80	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 40$ Vdc, $V_{EB(off)} = 4.0$ Vdc) ($V_{CE} = 40$ Vdc, $V_{EB(off)} = 4.0$ Vdc, $T_A = 100°C$) ($V_{CE} = 60$ Vdc, $V_{EB(off)} = 4.0$ Vdc) ($V_{CE} = 60$ Vdc, $V_{EB(off)} = 4.0$ Vdc, $T_A = 100°C$)	 2N3506 2N3507 	I_{CEX}	 — — — —	 1.0 150 1.0 150	μAdc
Base Cutoff Current ($V_{CE} = 40$ Vdc, $V_{EB(off)} = 4.0$ Vdc) ($V_{CE} = 60$ Vdc, $V_{EB(off)} = 4.0$ Vdc)	 2N3506 2N3507	I_{BL}	 — —	 1.0 1.0	μAdc
ON CHARACTERISTICS					
DC Current Gain(1) ($I_C = 500$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1.5$ Adc, $V_{CE} = 2.0$ Vdc) ($I_C = 2.5$ Adc, $V_{CE} = 3.0$ Vdc) ($I_C = 3.0$ Adc, $V_{CE} = 5.0$ Vdc)	 2N3506 2N3507 2N3506 2N3507 2N3506 2N3507 2N3506 2N3507	h_{FE}	 50 35 40 30 30 25 25 20	 — — 200 150 — — — —	—
Collector-Emitter Saturation Voltage(1) ($I_C = 500$ mAdc, $I_B = 50$ mAdc) ($I_C = 1.5$ Adc, $I_B = 150$ mAdc) ($I_C = 2.5$ Adc, $I_B = 250$ mAdc)		$V_{CE(sat)}$	— — —	0.5 1.0 1.5	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 500$ mAdc, $I_B = 50$ mAdc) ($I_C = 1.5$ Adc, $I_B = 150$ mAdc) ($I_C = 2.5$ Adc, $I_B = 250$ mAdc)		$V_{BE(sat)}$	— 0.9 —	1.0 1.4 2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 100$ mAdc, $V_{CE} = 5$ Vdc, f = 20 MHz)		f_T	60	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)		C_{obo}	—	40	pF
Input Capacitance ($V_{BE} = 3$ Vdc, $I_C = 0$, f = 100 kHz)		C_{ibo}	—	300	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

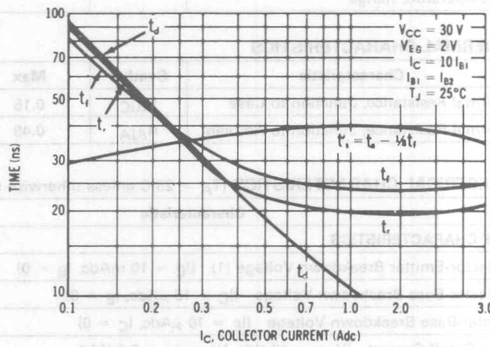
Characteristic		Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS					
Delay Time	I_C = 1.5 Adc, I_{B1} = 150 mAdc	t_d	—	15	ns
Rise Time	V_{CC} = 30 V, V_{EB} = 0 V	t_r	—	30	ns
Storage Time	I_C = 1.5 Adc, I_{B1} = I_{B2} = 150 mAdc	t_s	—	55	ns
Fall Time	V_{CC} = 30 V	t_f	—	35	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

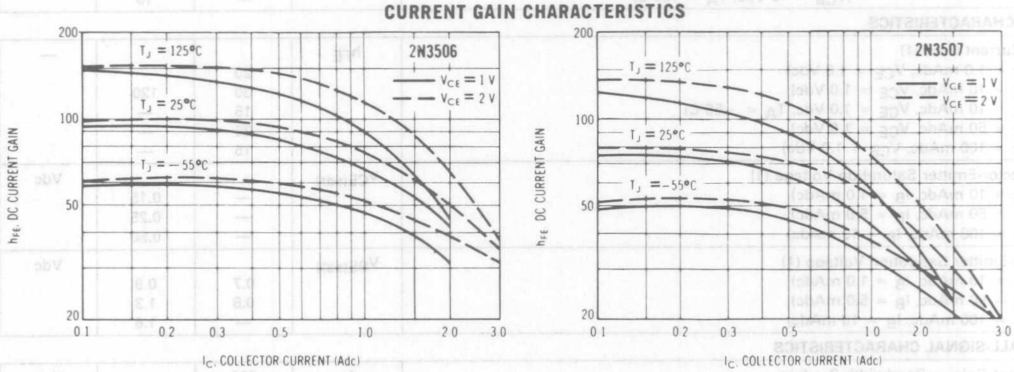
SATURATION VOLTAGES



SWITCHING TIMES

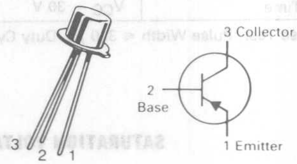


CURRENT GAIN CHARACTERISTICS



2N3546

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	12	Vdc
Collector-Base Voltage	V_{CBO}	15	Vdc
Emitter-Base Voltage	V_{EBO}	4.5	Vdc
DC Collector Current	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.36 2.06	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.2 6.9	Watts mW/°C
Operating and Storage Temperature Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.15	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	0.49	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	12	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	15	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	4.5	—	Vdc
Base Cutoff Current ($V_{CE} = 10$ Vdc, $V_{BE(off)} = 3.0$ Vdc)	I_{BEV}	—	0.10	μAdc
Collector Cutoff Current ($V_{CE} = 10$ Vdc, $V_{BE(off)} = 3.0$ Vdc)	I_{CEX}	—	0.010	μAdc
Collector Cutoff Current ($V_{CB} = 10$ Vdc) ($V_{CB} = 10$ Vdc, $T_A = 150°C$)	I_{CBO}	— —	0.010 10	μAdc
ON CHARACTERISTICS				
DC Current Gain (1) ($I_C = 1.0$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc, $T_A = -55°C$) ($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	 20 30 15 25 15	 — 120 — — —	—
Collector-Emitter Saturation Voltage (1) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc) ($I_C = 100$ mAdc, $I_B = 10$ mAdc)	$V_{CE(sat)}$	 — — —	 0.15 0.25 0.50	Vdc
Base-Emitter Saturation Voltage (1) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc) ($I_C = 100$ mAdc, $I_B = 10$ mAdc)	$V_{BE(sat)}$	 0.7 0.8 —	 0.9 1.3 1.6	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	700	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{obo}	—	6.0	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)	C_{ibo}	—	5.0	pF

SWITCHING CHARACTERISTICS

Delay Time	$I_C = 50$ mA, $I_{B1} = 5.0$ mA $V_{BE} = 2.0$ V, $V_{CC} = 3.0$ V	t_d	—	10	ns
Rise Time		t_r	—	15	ns
Storage Time	$I_C = 50$ mA, $I_{B1} = I_{B2} = 5.0$ mA $V_{CC} = 3.0$ V	t_s	—	20	ns
Fall Time		t_f	—	15	ns
Turn-On Time		t_{on}	—	40	ns
Turn-Off Time		t_{off}	—	30	ns
Total Control Charge ($I_C = 50$ mA, $I_B = 5.0$ mA, $V_{CC} = 3.0$ V)		Q_T	—	400	pC

(1) Pulse Test: PW = 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1

LIMITS OF SATURATION VOLTAGES

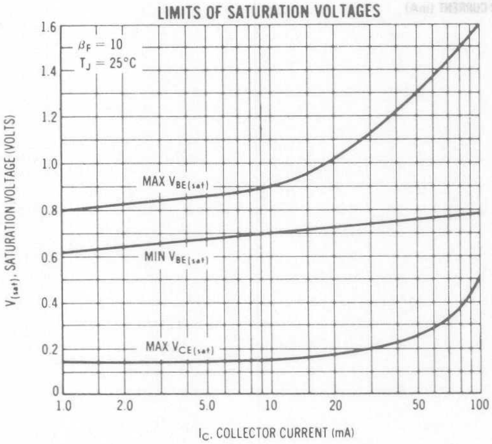


FIGURE 2

STORAGE TIME BEHAVIOR

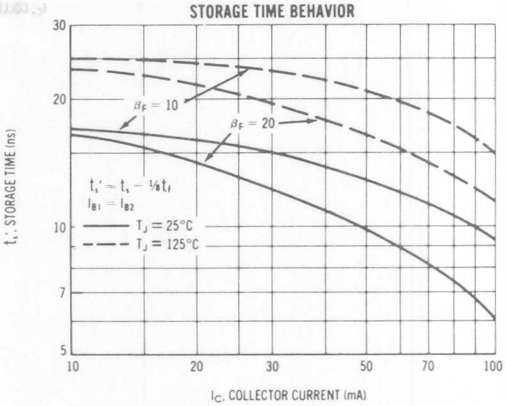
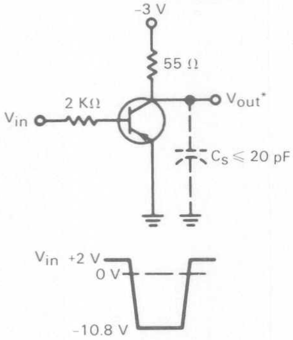


FIGURE 3

DELAY AND RISE TIME EQUIVALENT TEST CIRCUIT

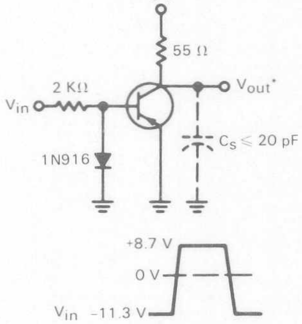


PULSE WIDTH = 200 ns
RISE TIME ≤ 2 ns
DUTY CYCLE ≤ 10%

*OSCILLOSCOPE RISE TIME ≤ 1 ns

FIGURE 4

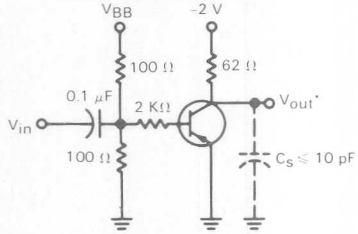
STORAGE AND FALL TIME EQUIVALENT TEST CIRCUIT



PULSE WIDTH = 200 ns
RISE TIME ≤ 2 ns
DUTY CYCLE ≤ 10%

FIGURE 5

SWITCHING TIME TEST CIRCUIT



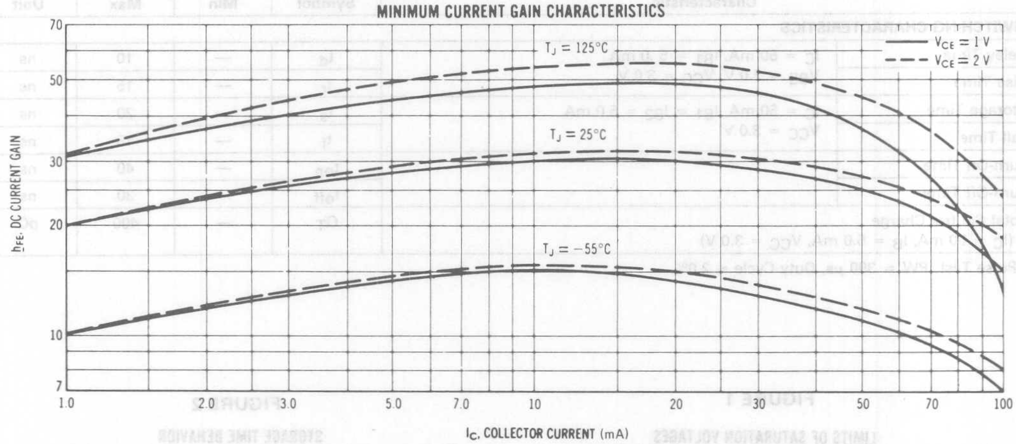
PULSE WIDTH > 200 ns
RISE TIME < 2 ns
$Z_{in} = 50$ Ω

t_{on}: $V_{BB} = +3$ V, $V_{in} = -7$ V
t_{off}: $V_{BB} = -4$ V, $V_{in} = +6$ V

4

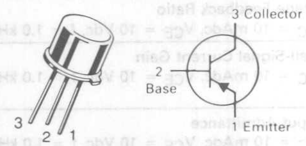
FIGURE 6

MINIMUM CURRENT GAIN CHARACTERISTICS



2N3634 thru 2N3637

JAN, JTX AVAILABLE
CASE 79-02, STYLE 1
TO-39 (TO-39-205AD)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

4

MAXIMUM RATINGS

Rating	Symbol	2N3634 2N3635	2N3636 2N3637	Unit
Collector-Emitter Voltage	V_{CEO}	140	175	Vdc
Collector-Base Voltage	V_{CBO}	140	175	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	1.0		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 5.71		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5.0 28.6		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	2N3634, 2N3635 2N3636, 2N3637	$V_{(BR)CEO}$	140 175	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	2N3634, 2N3635 2N3636, 2N3637	$V_{(BR)CBO}$	140 175	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 100$ Vdc, $I_E = 0$)		I_{CBO}	—	100	nAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)		I_{EBO}	—	50	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) ($I_C = 0.1$ mAdc, $V_{CE} = 10$ Vdc)	2N3634, 2N3636 2N3635, 2N3637	h_{FE}	40 80	— —	—
($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc)	2N3634, 2N3636 2N3635, 2N3637		45 90	— —	
($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc)	2N3634, 2N3636 2N3635, 2N3637		50 100	— —	
($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc)	2N3634, 2N3636 2N3635, 2N3637		50 100	150 300	
($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)	2N3634, 2N3636 2N3635, 2N3637		25 50	— —	
Collector-Emitter Saturation Voltage(1) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)		$V_{CE(sat)}$	— —	0.3 0.5	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)		$V_{BE(sat)}$	— 0.65	0.8 0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($V_{CE} = 30$ Vdc, $I_C = 30$ mAdc, f = 100 MHz)	2N3634, 2N3636 2N3635, 2N3637	f_T	150 200	— —	MHz

Characteristic		Symbol	Min	Max	Unit
Output Capacitance (V_{CB} = 20 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	10	pF
Input Capacitance (V_{BE} = 1.0 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	75	pF
Input Impedance (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3634, 2N3636 2N3635, 2N3637	h_{ie}	100 200	600 1200	ohms
Voltage Feedback Ratio (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{re}	—	3.0	$\times 10^{-4}$
Small-Signal Current Gain (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3634, 2N3636 2N3635, 2N3637	h_{fe}	40 80	160 320	—
Output Admittance (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{oe}	—	200	μmhos
Noise Figure (I_C = 0.5 mAdc, V_{CE} = 10 Vdc, R_S = 1.0 k ohms, f = 1.0 kHz)		NF	—	3.0	dB
SWITCHING CHARACTERISTICS					
Turn-On Time	(V_{CC} = 100 Vdc, V_{BE} = 4.0 Vdc, I_C = 50 mAdc, I_{B1} = I_{B2} = 5.0 mAdc)	t_{on}	—	400	ns
Turn-Off Time		t_{off}	—	600	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — JUNCTION CAPACITANCE VARIATIONS

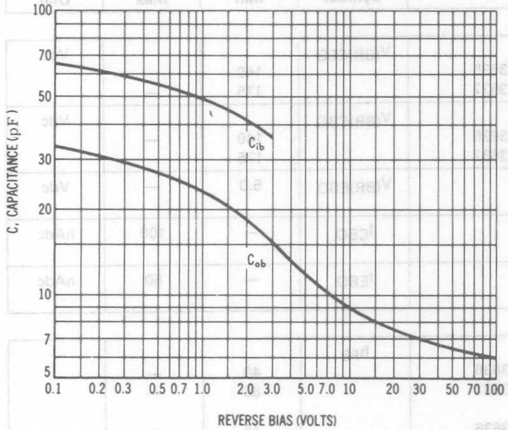


FIGURE 2 — GAIN-BANDWIDTH PRODUCT

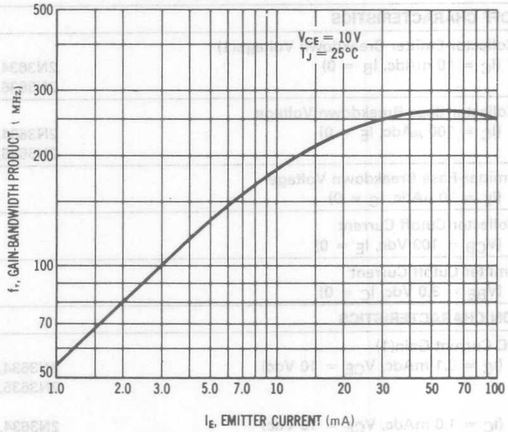
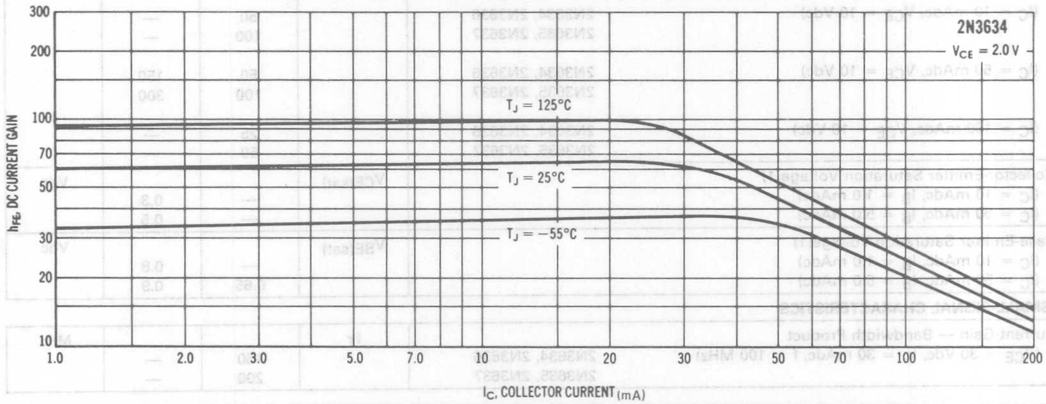


FIGURE 3 — CURRENT GAIN CHARACTERISTICS versus JUNCTION TEMPERATURE



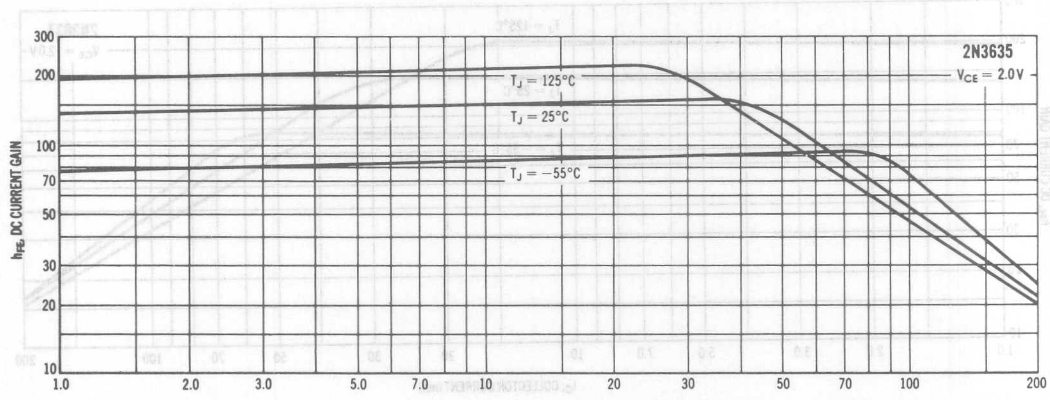


FIGURE 4 — CURRENT GAIN CHARACTERISTICS versus COLLECTOR EMITTER VOLTAGE

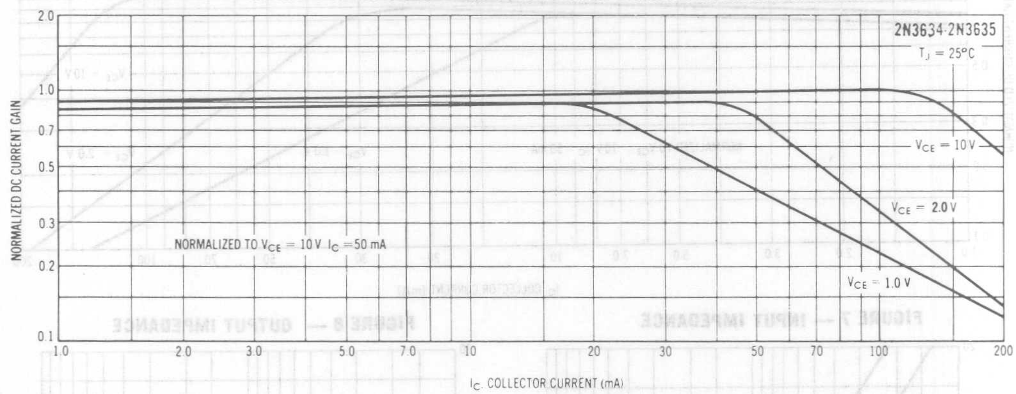
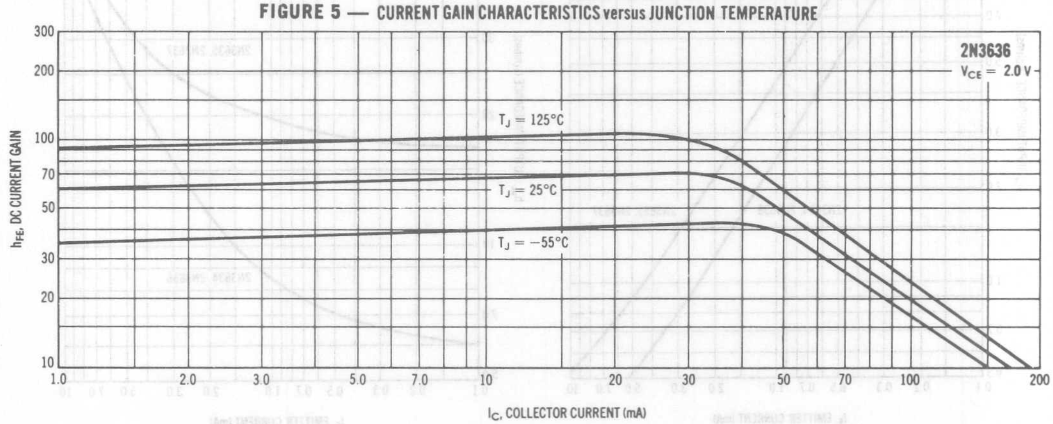


FIGURE 5 — CURRENT GAIN CHARACTERISTICS versus JUNCTION TEMPERATURE



4

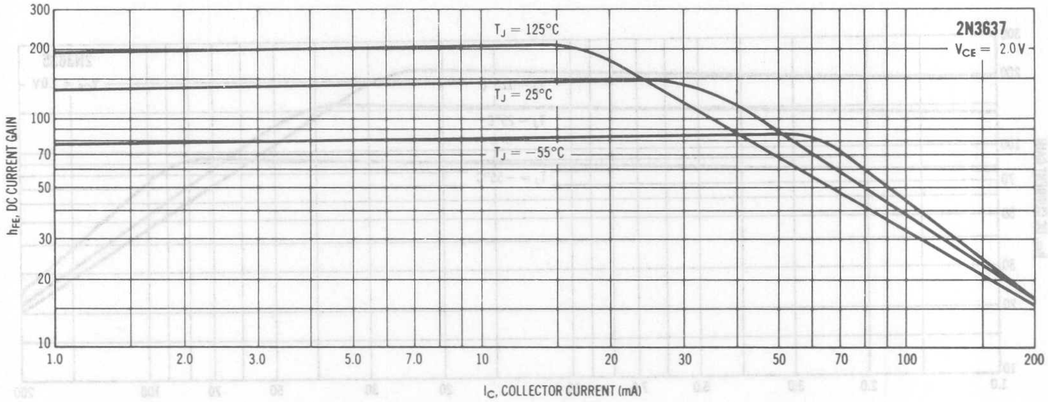


FIGURE 6 — CURRENT GAIN CHARACTERISTICS versus COLLECTOR EMITTER VOLTAGE

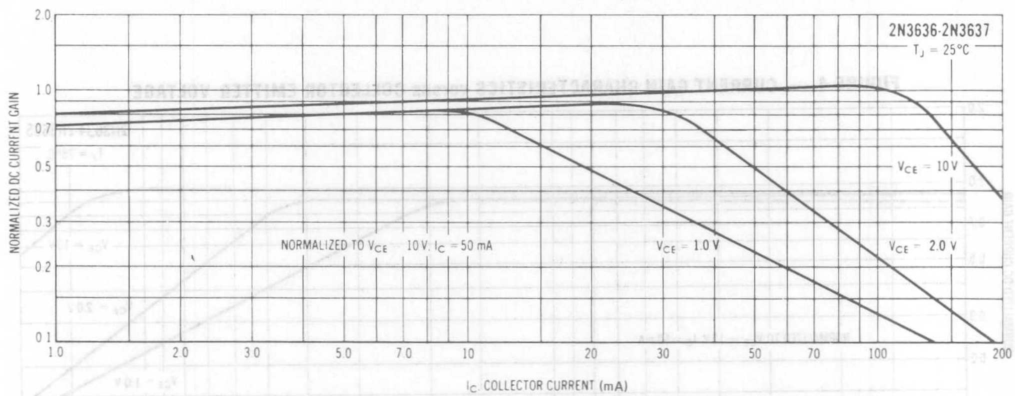


FIGURE 7 — INPUT IMPEDANCE

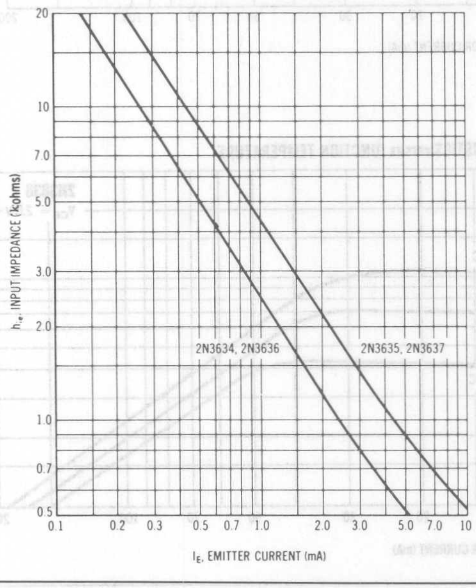


FIGURE 8 — OUTPUT IMPEDANCE

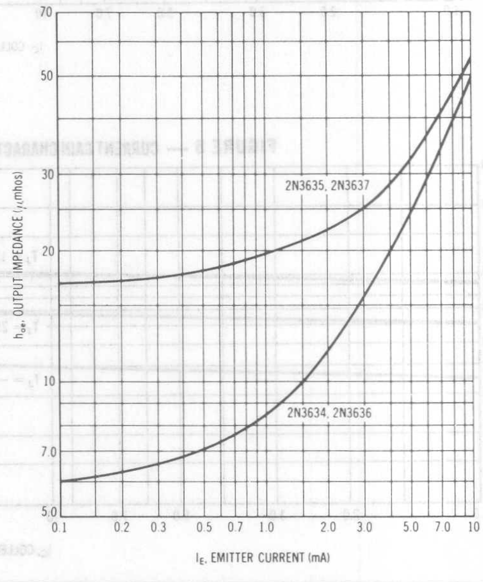


FIGURE 9 — CURRENT GAIN

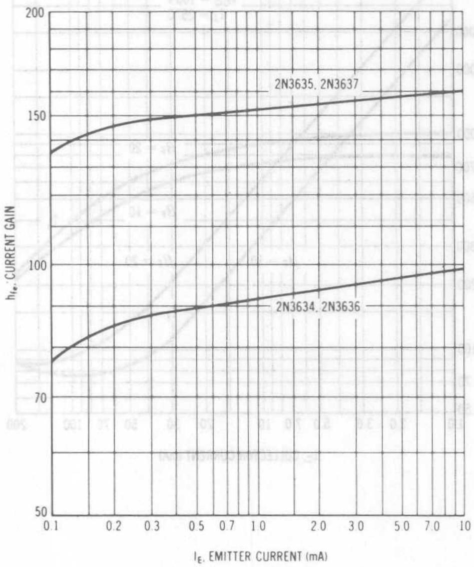


FIGURE 10 — VOLTAGE FEEDBACK RATIO

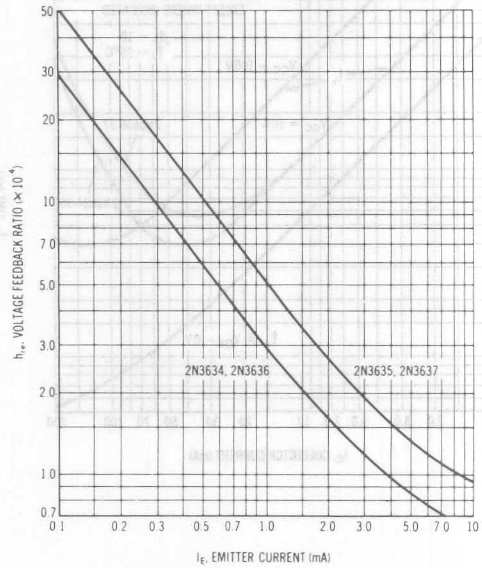


FIGURE 11 — SATURATION VOLTAGES

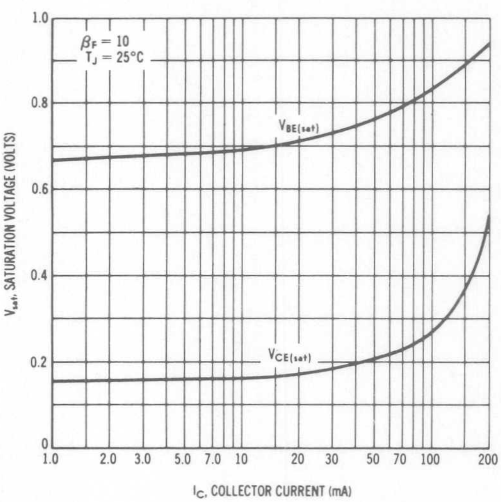


FIGURE 12 — TEMPERATURE COEFFICIENTS

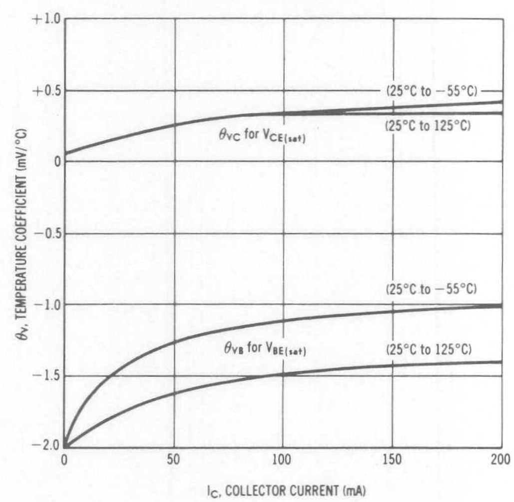
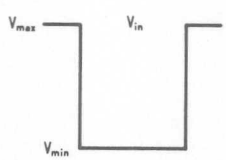


FIGURE 13 — SWITCHING TIME TEST CIRCUIT



P.W. ≅ 20 µs
DUTY CYCLE ≤ 2%
RISE TIME ≤ 20 ns

	V_{max}	V_{min}
TURN-ON	+4.0 V	−5.65 V
TURN-OFF	+4.1 V	−5.9 V

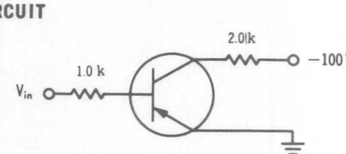


FIGURE 14 — TURN-ON TIME VARIATIONS WITH VOLTAGE

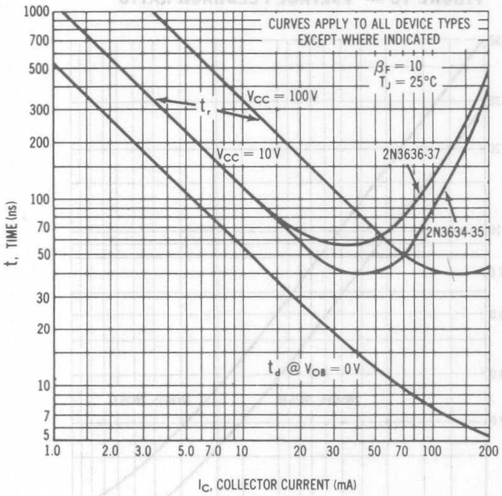
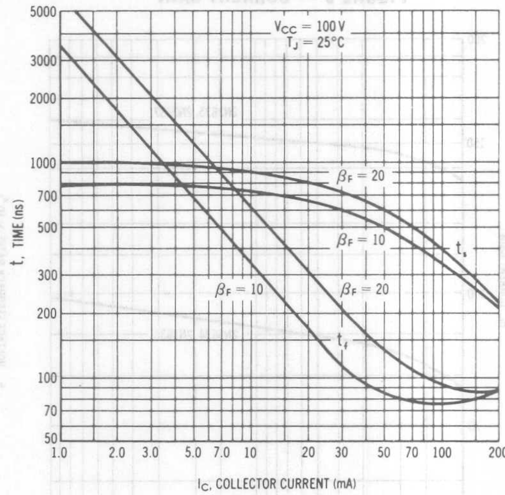
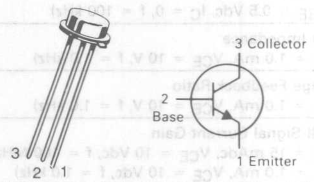


FIGURE 15 — TURN-OFF TIME VARIATIONS WITH CIRCUIT GAIN*



2N3648

CASE 26-03, STYLE 1
TO-46 (TO-206AB)



SWITCHING TRANSISTOR

NPN SILICON

4

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	500	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	400 2.28	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.0 11.43	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	15	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current (V_{CE} = 10 Vdc, $V_{EB(off)}$ = 1.0 Vdc) (V_{CE} = 10 Vdc, $V_{EB(off)}$ = 1.0 Vdc, T_A = 150°C)	I_{CEX}	 — —	 0.025 50	μAdc
Base Cutoff Current (V_{CE} = 10 Vdc, V_{OB} = 1.0 Vdc)	I_{BL}	—	0.025	μAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc) (I_C = 150 mAdc, V_{CE} = 1.0 Vdc) (I_C = 150 mAdc, V_{CE} = 1.0 Vdc, T_A = −55°C) (I_C = 500 mAdc, V_{CE} = 1.0 Vdc)	h_{FE}	 15 25 30 12 12	 — — 120 — —	—
Collector-Emitter Saturation Voltage(1) (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)	$V_{CE(sat)}$	 — — —	 0.25 0.4 0.8	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)	$V_{BE(sat)}$	 — 0.8 —	 0.8 1.0 1.5	Vdc

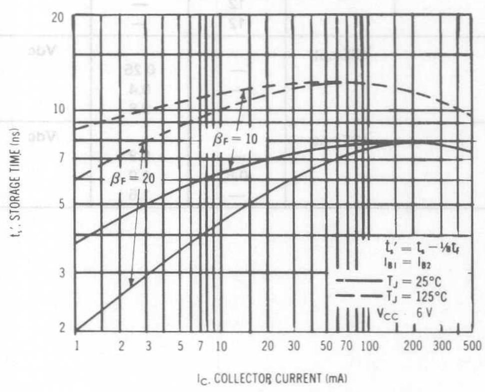
4

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

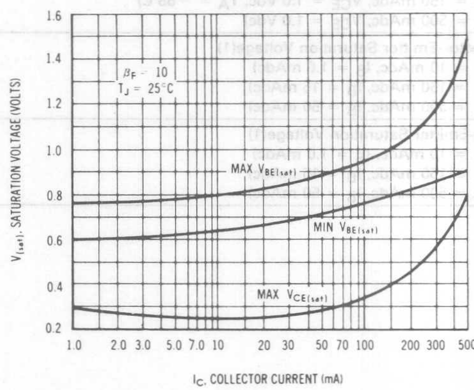
Characteristic		Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	4.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	8.0	pF
Input Impedance (I_C = 1.0 mA, V_{CE} = 10 V, f = 1.0 kHz)		h_{ie}	0.6	4.5	kohms
Voltage Feedback Ratio (I_C = 1.0 mA, V_{CE} = 10 V, f = 1.0 kHz)		h_{re}	—	25	$X\ 10^{-4}$
Small-Signal Current Gain		h_{fe}			—
(I_C = 15 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)			4.5	—	
(I_C = 1.0 mA, V_{CE} = 10 Vdc, f = 1.0 kHz)			20	150	
Output Admittance (I_C = 1.0 mA, V_{CE} = 10 V, f = 1.0 kHz)		h_{oe}	10	100	µmhos
SWITCHING CHARACTERISTICS					
Delay Time	(I_C = 150 mA, I_{B1} = 15 mA, V_{EB} = 0.5 V, V_{CC} = 6.0 V)	t_d	—	8.0	ns
Rise Time		t_r	—	10	ns
Storage Time	(I_C = 150 mA, I_{B1} = $-I_{B2}$ = 15 mA, V_{CC} = 6.0 V)	t_s	—	12	ns
Fall Time		t_f	—	8.0	ns
Turn-On Time	(I_C = 150 mA, I_{B1} = 15 mA, V_{EB} = 0.5 V, V_{CC} = 6.0 V)	t_{on}	—	16	ns
Turn-Off Time	(I_C = 150 mA, I_{B1} = $-I_{B2}$ = 15 mA, V_{CC} = 6.0 V)	t_{off}	—	18	ns
Total Control Charge (I_C = 150 mA, I_B = 15 mA, V_{CC} = 6.0 V)		Q_T	—	300	pC

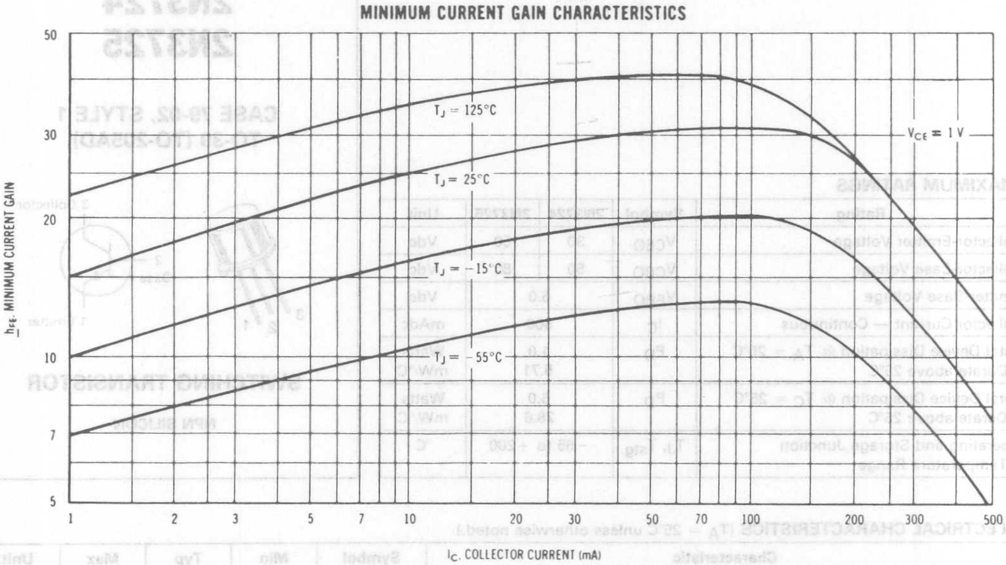
(1) Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.

STORAGE TIME VARIATION



LIMITS OF SATURATION VOLTAGE

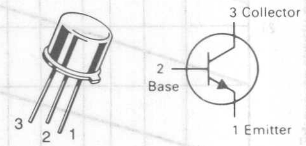



MINIMUM CURRENT GAIN CHARACTERISTICS
T_J = 125°C
T_J = 25°C
T_J = −15°C
T_J = −55°C
V_{CE} = 1 V
h_{FE}, MINIMUM CURRENT GAIN
50
30
20
10
7
5
1
2
3
5
7
10
20
30
50
70
100
200
300
500
I_C, COLLECTOR CURRENT (mA)

2N3700 For Specifications, See 2N3019 Data.

2N3724
2N3725

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



SWITCHING TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	2N3724	2N3725	Unit
Collector-Emitter Voltage	V_{CEO}	30	50	Vdc
Collector-Base Voltage	V_{CBO}	50	80	Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 5.71		Watts mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5.0 28.6		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	 2N3725 2N3724	$V_{(BR)CEO}$	 50 30	 — —	 — —	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 10$ μAdc, $V_{BE} = 0$)	 2N3725 2N3724	$V_{(BR)CES}$	 80 50	 — —	 — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	 2N3725 2N3724	$V_{(BR)CBO}$	 80 50	 — —	 — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	6.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 60$ Vdc, $I_E = 0$) ($V_{CB} = 40$ Vdc, $I_E = 0$) ($V_{CB} = 60$ Vdc, $I_E = 0$, $T_A = 100°C$) ($V_{CB} = 60$ Vdc, $I_E = 0$, $T_A = 100°C$)	 2N3725 2N3724 2N3725 2N3724	I_{CBO}	 — — — —	 0.12 0.12 — —	 1.7 1.7 120 120	μAdc
Collector Cutoff Current ($V_{CE} = 80$ Vdc, $V_{EB} = 0$) ($V_{CE} = 50$ Vdc, $V_{EB} = 0$)	 2N3725 2N3724	I_{CES}	 — —	 0.15 0.15	 10 10	μAdc
Base Current ($V_{CE} = 50$ V, $V_{EB} = 0$) ($V_{CE} = 80$ V, $V_{EB} = 0$)	 2N3724 2N3725	I_B	—	—	10	μAdc
ON CHARACTERISTICS(1)						
DC Current Gain ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc, $T_A = -55°C$) ($I_C = 300$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 500$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 500$ mAdc, $V_{CE} = 1.0$ Vdc, $T_A = -55°C$) ($I_C = 800$ mAdc, $V_{CE} = 2.0$ Vdc) ($I_C = 1.0$ Adc, $V_{CE} = 5.0$ Vdc) ($I_C = 800$ mA, $V_{CE} = 2.0$ V) ($I_C = 1.0$ Adc, $V_{CE} = 5.0$ V)	 2N3725 2N3725	h_{FE}	 30 60 30 40 35 20 25 30 20 25	 — — — — — — — — — —	 — 150 — — — — — — — —	—

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

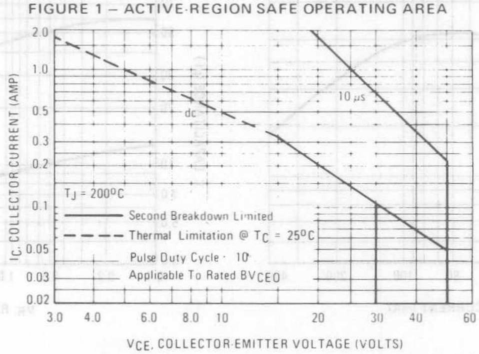
Characteristic		Symbol	Min	Typ	Max	Unit
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$				Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)	2N3725		—	0.17	0.25	
	2N3724		—	0.17	0.25	
(I_C = 100 mAdc, I_B = 10 mAdc)	2N3725		—	0.19	0.26	
	2N3724			0.19	0.20	
(I_C = 300 mAdc, I_B = 30 mAdc)	2N3725		—	0.25	0.40	
	2N3724		—	0.25	0.32	
(I_C = 500 mAdc, I_B = 50 mAdc)	2N3725		—	0.30	0.52	
	2N3724			0.30	0.42	
(I_C = 800 mAdc, I_B = 80 mAdc)	2N3725		—	0.43	0.80	
	2N3724		—	0.43	0.65	
(I_C = 1.0 mAdc, I_B = 100 mAdc)	2N3725		—	0.55	0.95	
	2N3724			0.55	0.75	
Base-Emitter Saturation Voltage		$V_{BE(sat)}$				Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)					0.76	
(I_C = 100 mAdc, I_B = 10 mAdc)			—	—	0.86	
(I_C = 300 mAdc, I_B = 30 mAdc)			—	—	1.1	
(I_C = 500 mAdc, I_B = 50 mAdc)			0.8	—	1.1	
(I_C = 800 mAdc, I_B = 80 mAdc)			—	—	1.5	
(I_C = 1.0 Adc, I_B = 100 mAdc)			—	—	1.7	
SMALL SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product(2) (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	300	—	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	2N3725	C_{obo}	—	—	10	pF
	2N3724		—	—	12	
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	—	55	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 1.0%.
(2) $f_T = |h_{fe}| \cdot f_{test}$.

SWITCHING CHARACTERISTICS

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Delay Time	(V_{CC} = 30 Vdc, $V_{BE(off)}$ = 3.8 Vdc, I_C = 500 mAdc, I_{B1} = 50 mAdc) (Figures 8, 10)	t_d	–	5.0	10	ns
Rise Time		t_r	–	15	30	ns
Turn-On Time		t_{on}	–	20	35	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 500 mAdc, $I_{B1} = I_{B2}$ = 50 mAdc) (Figures 9, 10)	t_s		35	50	ns
Fall Time		t_f	–	20	25	ns
Turn-Off Time		t_{off}	–	50	60	ns

FIGURE 1 – ACTIVE-REGION SAFE OPERATING AREA



TYPICAL DC CHARACTERISTICS

FIGURE 2 – DC CURRENT GAIN

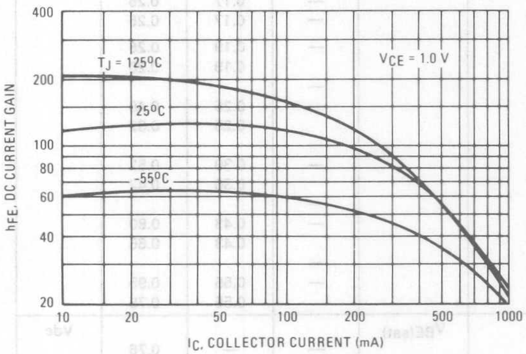


FIGURE 3 – "ON" VOLTAGES

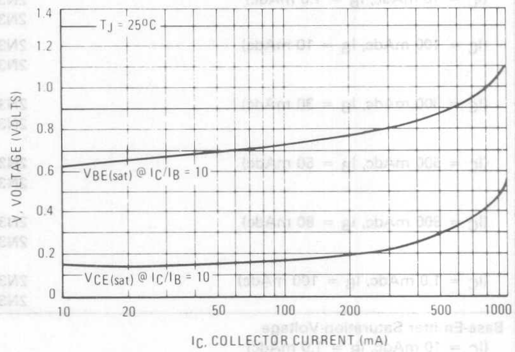


FIGURE 4 – COLLECTOR SATURATION REGION

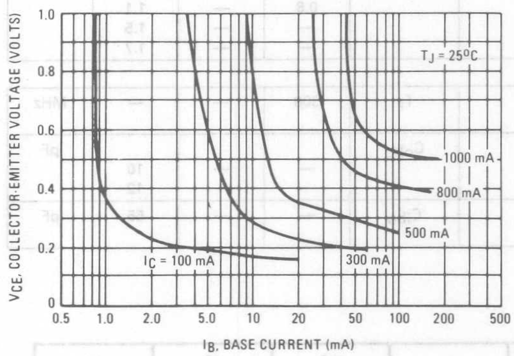
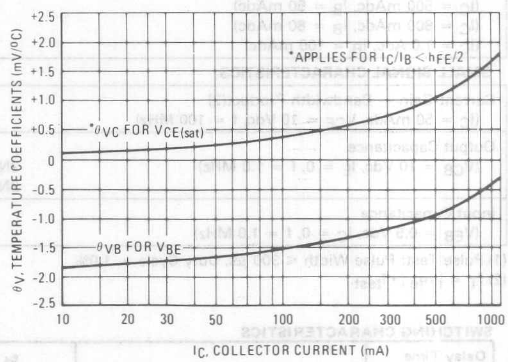


FIGURE 5 – TEMPERATURE COEFFICIENTS



TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 6 – CURRENT-GAIN – BANDWIDTH PRODUCT

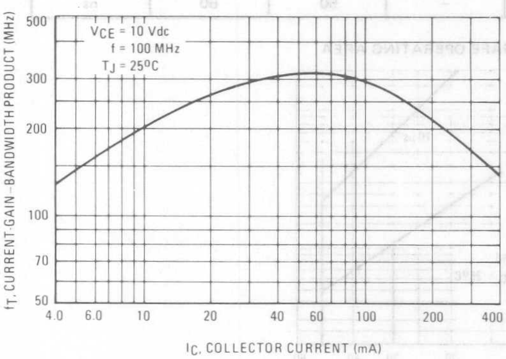


FIGURE 7 – CAPACITANCE

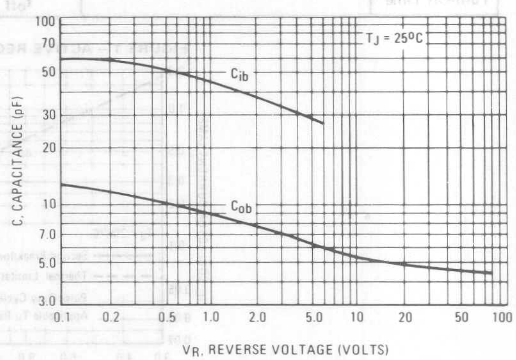


FIGURE 8 – TURN-ON TIME

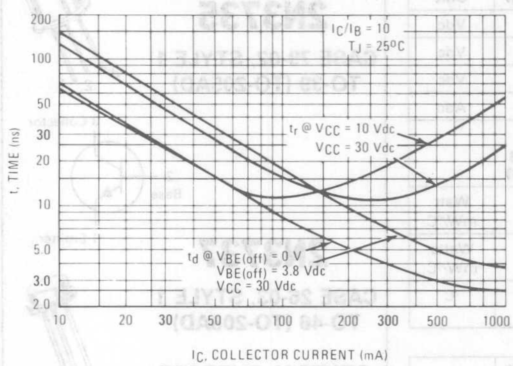
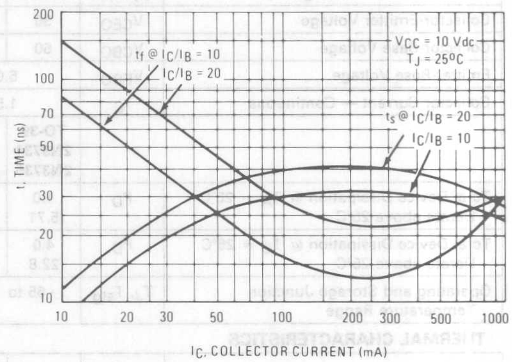


FIGURE 9 – TURN-OFF TIME



4

FIGURE 10 – SWITCHING TIME TEST CIRCUIT

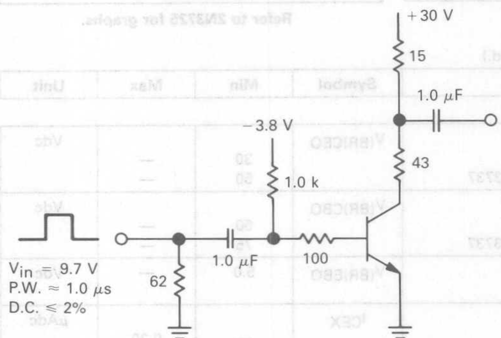
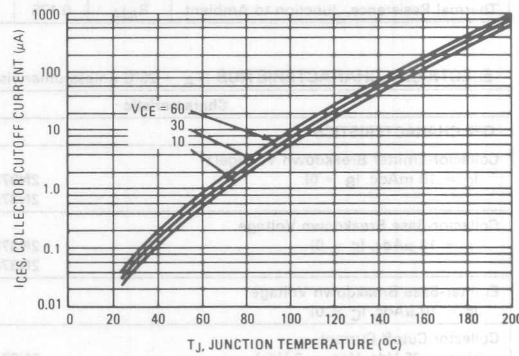
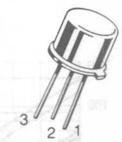


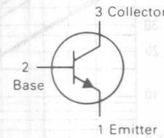
FIGURE 11 – COLLECTOR CUTOFF CURRENT



2N3734
2N3735

CASE 79-02, STYLE 1
TO-39 (TO-205AD)





2N3737

CASE 26-03, STYLE 1
TO-46 (TO-206AD)

GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N3725 for graphs.

MAXIMUM RATINGS

Rating	Symbol	2N3734	2N3735 2N3737	Unit
Collector-Emitter Voltage	V_{CEO}	30	50	Vdc
Collector-Base Voltage	V_{CBO}	50	75	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	1.5		Adc
		TO-39 2N3734 2N3735	TO-46 2N3737	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 5.71	0.5 2.86	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	4.0 22.8	2.0 11.4	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	2N3734	2N3735 2N3737	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.044	0.088	°C/mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	0.175	0.35	°C/mW

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	 2N3734 2N3735, 2N3737	$V_{(BR)CEO}$	 30 50	 — —	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	 2N3734 2N3735, 2N3737	$V_{(BR)CBO}$	 50 75	 — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CE} = 25 Vdc, V_{EB} = 2 Vdc) (V_{CE} = 25 Vdc, V_{EB} = 2 Vdc, T_A = 100°C) (V_{CE} = 40 Vdc, V_{EB} = 2 Vdc) (V_{CE} = 40 Vdc, V_{EB} = 2 Vdc, T_A = 100°C)	 2N3734 2N3735, 2N3737 	I_{CEX}	 — — — —	 0.20 20 0.20 20	μAdc
Base Cutoff Current (V_{CE} = 25 Vdc, V_{EB} = 2 Vdc) (V_{CE} = 40 Vdc, V_{EB} = 2 Vdc)	 2N3734 2N3735, 2N3737	I_{BL}	 — —	 0.3 0.3	μAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 10 mAdc, V_{CE} = 1 Vdc) (I_C = 150 mAdc, V_{CE} = 1 Vdc) (I_C = 500 mAdc, V_{CE} = 1 Vdc) (I_C = 1 Adc, V_{CE} = 1.5 Vdc) (I_C = 1.5 Adc, V_{CE} = 5 Vdc) 	 2N3734 2N3735, 2N3737 2N3734 2N3735, 2N3737	h_{FE}	 35 40 35 30 20 30 20	 — — — 120 80 — —	—
Collector-Emitter Saturation Voltage(1) (I_C = 10 mAdc, I_B = 1 mAdc) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc) (I_C = 1 Adc, I_B = 100 mAdc)		$V_{CE(sat)}$	 — — — —	 0.2 0.3 0.5 0.9	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 10 mAdc, I_B = 1 mAdc) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc) (I_C = 1 Adc, I_B = 100 mAdc)		$V_{BE(sat)}$	 — — — 0.9	 0.8 1.0 1.2 1.4	Vdc

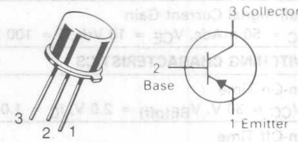
Characteristic	Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	9.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)	C_{ibo}	—	80	pF
Small-Signal Current Gain (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	h_{fe}	2.5	—	—
SWITCHING CHARACTERISTICS				
Turn-On Time (V_{CC} = 30 V, $V_{BE(off)}$ = 2.0 V, I_C = 1.0 Amp, I_{B1} = 100 mA)	t_{on}	—	40	ns
Turn-Off Time (V_{CC} = 30 V, $V_{BE(off)}$ = 2.0 V, I_C = 1.0 Amp, I_{B1} = 100 mA)	t_{off}	—	60	ns
Total Control Charge (I_C = 1 Amp, I_B = 100 mA, V_{CC} = 30 V)	Q_T	—	10	NC

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

4

2N3743

JAN, JTX AVAILABLE
CASE 79-02, STYLE 1
TO-39 (TO-205AD)



AMPLIFIER TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	300	Vdc
Collector-Base Voltage	V_{CBO}	300	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	50	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 5.7	Watts mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5.0 28.6	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	300	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	300	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 200$ Vdc, $I_E = 0$) ($V_{CB} = 200$ Vdc, $I_E = 0$, $T_A = 100°C$)	I_{CBO}	 — —	 0.3 30	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain(2) ($I_C = 100$ μAdc, $V_{CE} = 10$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 30$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 50$ mAdc, $V_{CE} = 20$ Vdc)	h_{FE}	 20 25 25 25 25	 — — — 250 —	—
Collector-Emitter Saturation Voltage(2) ($I_C = 10$ mAdc, $I_B = 1$ mAdc) ($I_C = 30$ mAdc, $I_B = 3$ mAdc)	$V_{CE(sat)}$	 — —	 5.0 8.0	Vdc
Base-Emitter Saturation Voltage(2) ($I_C = 10$ mAdc, $I_B = 1$ mAdc) ($I_C = 30$ mAdc, $I_B = 3$ mAdc)	$V_{BE(sat)}$	 — —	 1.0 1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance ($V_{CB} = 20$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	15	pF
Input Capacitance ($V_{EB} = 1.0$ Vdc, $I_C = 0$, f = 100 kHz)	C_{ibo}	—	400	pF
Input Impedance ($V_{CE} = 10$ V, $I_C = 10$ mA, f = 1 kHz)	h_{ie}	—	1.0	kohms
Voltage Feedback Ratio ($V_{CE} = 10$ V, $I_C = 10$ mA, f = 1 kHz)	h_{re}	—	4.0	$\times 10^{-4}$
Small-Signal Current Gain ($V_{CE} = 10$ V, $I_C = 10$ mA, f = 1 kHz)	h_{fe}	30	300	—

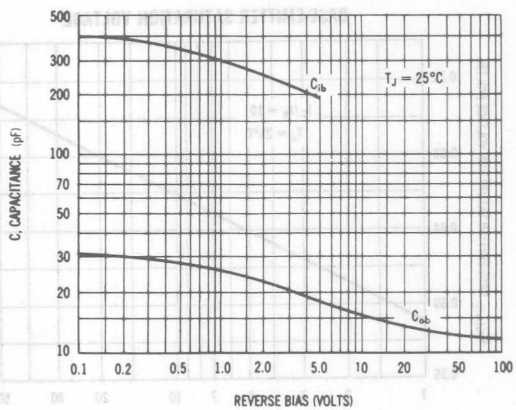
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Current Gain — High Frequency (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 20 MHz)	$\|h_{fe}\|$	1.5	—	—
Output Admittance (V_{CE} = 10 V, I_C = 10 mA, f = 1 kHz)	h_{oe}	—	200	μmhos
Real Part of Input Impedance (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 5 MHz)	$Re(h_{ie})$	—	40	ohms

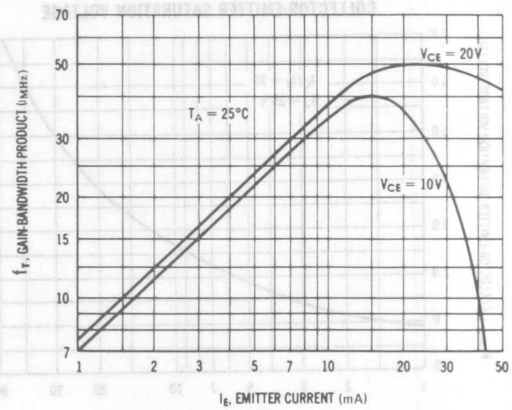
(1) PW ≤ 30 μs, Duty Cycle ≤ 1.0%.
(2) PW ≤ 300 μs, Duty Cycle ≤ 2.0%.

4

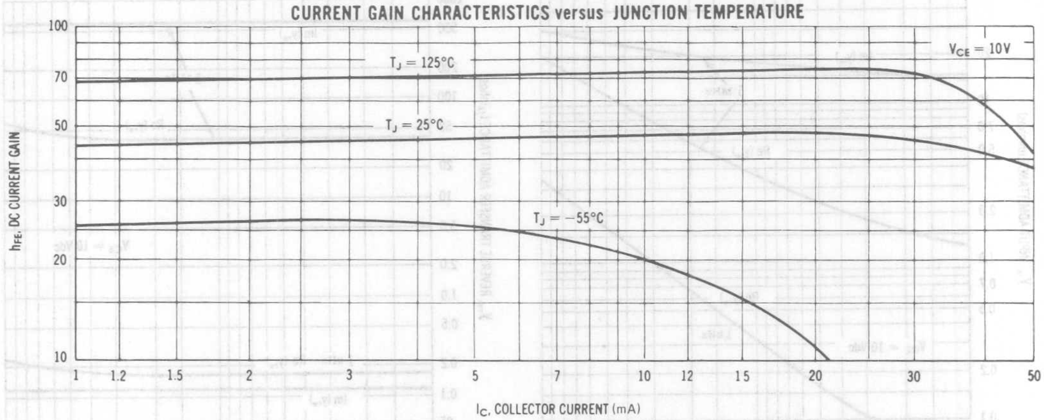
JUNCTION CAPACITANCE



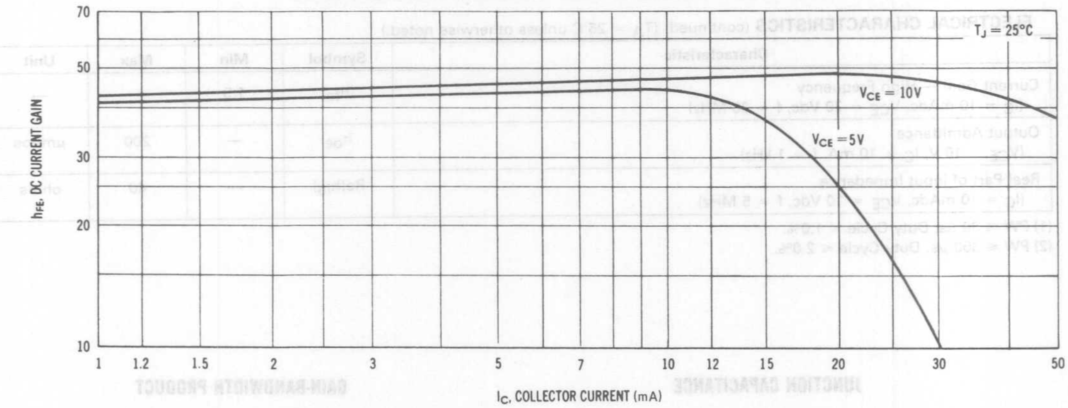
GAIN-BANDWIDTH PRODUCT



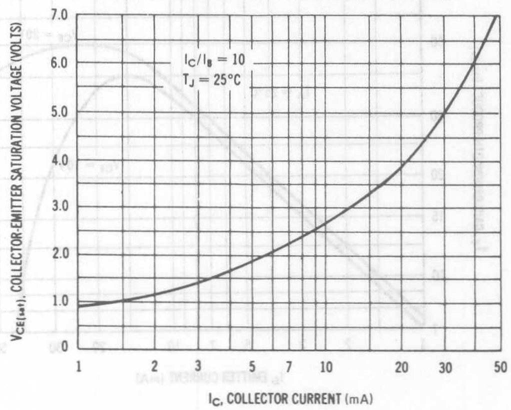
CURRENT GAIN CHARACTERISTICS versus JUNCTION TEMPERATURE



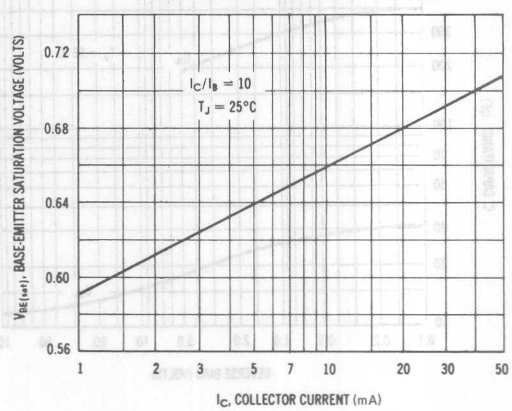
CURRENT GAIN CHARACTERISTICS versus COLLECTOR-EMITTER VOLTAGE



COLLECTOR-EMITTER SATURATION VOLTAGE



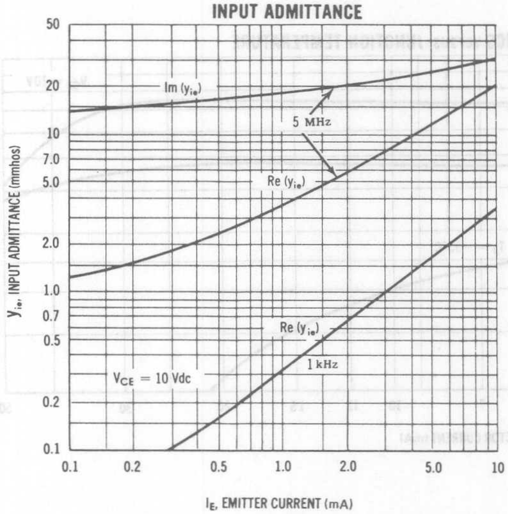
BASE-EMITTER SATURATION VOLTAGE



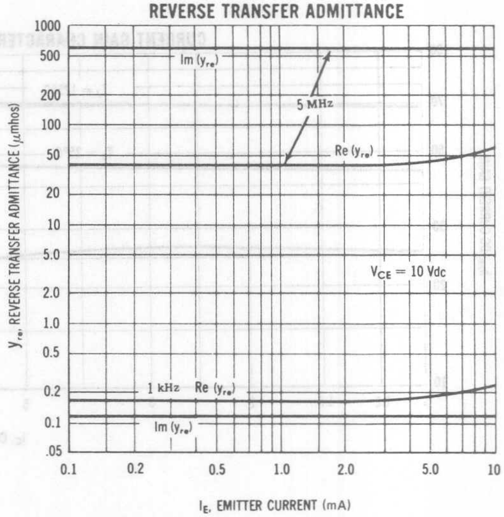
SMALL SIGNAL y PARAMETERS

$T_A = 25°C$

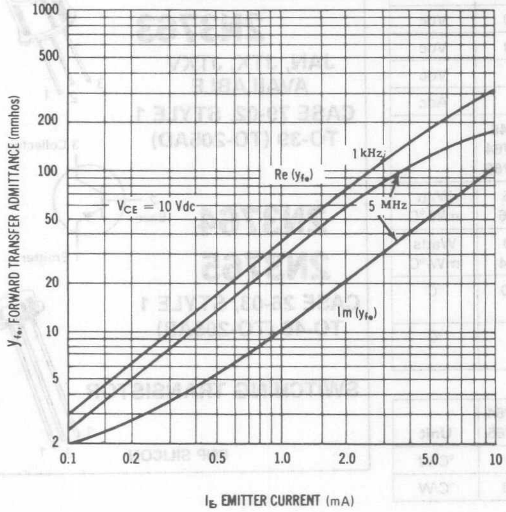
INPUT ADMITTANCE



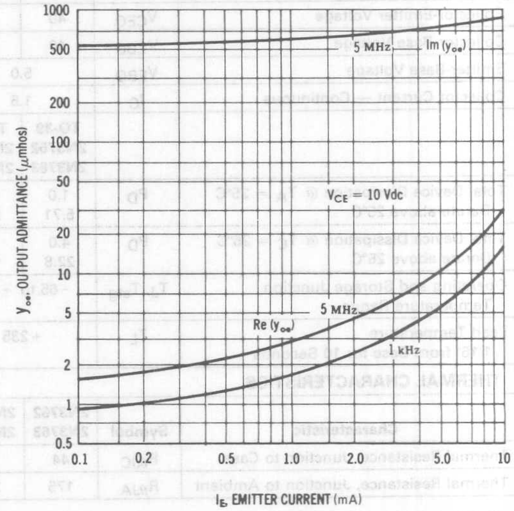
REVERSE TRANSFER ADMITTANCE



FORWARD TRANSFER ADMITTANCE



OUTPUT ADMITTANCE



4

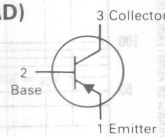
MAXIMUM RATINGS

Rating	Symbol	2N3762 2N3764	2N3763 2N3765	Unit
Collector-Emitter Voltage	V_{CEO}	40	60	Vdc
Collector-Base Voltage	V_{CBO}	40	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	1.5		Adc
		TO-39 2N3762 2N3763	TO-46 2N3764 2N3765	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 5.71	0.5 2.86	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	4.0 22.8	2.0 11.4	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C
Lead Temperature 1/16" from Case for 10 Seconds	T_L	+235		°C

2N3762
2N3763

JAN, JTX, JTXV AVAILABLE

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



2N3764
2N3765

CASE 26-03, STYLE 1
TO-46 (TO-206AB)

SWITCHING TRANSISTOR

PNP SILICON

THERMAL CHARACTERISTICS

Characteristic	Symbol	2N3762 2N3763	2N3764 2N3765	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	44	88	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	175	350	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	 2N3762, 2N3764 2N3763, 2N3765	$V_{(BR)CEO}$	 40 60	 — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	 2N3762, 2N3764 2N3763, 2N3765	$V_{(BR)CBO}$	 40 60	 — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 20$ Vdc, $V_{EB} = 2.0$ Vdc) ($V_{CE} = 20$ Vdc, $V_{EB} = 2.0$ Vdc, $T_A = 100°C$) ($V_{CE} = 30$ Vdc, $V_{EB} = 2.0$ Vdc) ($V_{CE} = 30$ Vdc, $V_{EB} = 2.0$ Vdc, $T_A = 100°C$)	 2N3762, 2N3764 2N3763, 2N3765 	I_{CEX}	 — — — —	 0.10 10 0.10 10	μAdc
Base Cutoff Current ($V_{CE} = 20$ Vdc, $V_{EB} = 2.0$ Vdc) ($V_{CE} = 30$ Vdc, $V_{EB} = 2.0$ Vdc)	 2N3762, 2N3764 2N3763, 2N3765	I_{BL}	 — —	 0.2 0.2	μAdc
ON CHARACTERISTICS					
DC Current Gain(1) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 150$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 500$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1.0$ Adc, $V_{CE} = 1.5$ Vdc) ($I_C = 1.5$ Adc, $V_{CE} = 5.0$ Vdc)	 2N3762, 2N3764 2N3763, 2N3765 2N3762, 2N3764 2N3763, 2N3765	h_{FE}	 35 40 35 30 20 30 20	 — — — 120 80 — —	—
Collector-Emitter Saturation Voltage(1) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc) ($I_C = 1.0$ Adc, $I_B = 100$ mAdc)		$V_{CE(sat)}$	 — — — —	 0.1 0.22 0.5 0.9	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc) ($I_C = 1.0$ Adc, $I_B = 100$ mAdc)		$V_{BE(sat)}$	 — — — 0.9	 0.8 1.0 1.2 1.4	Vdc

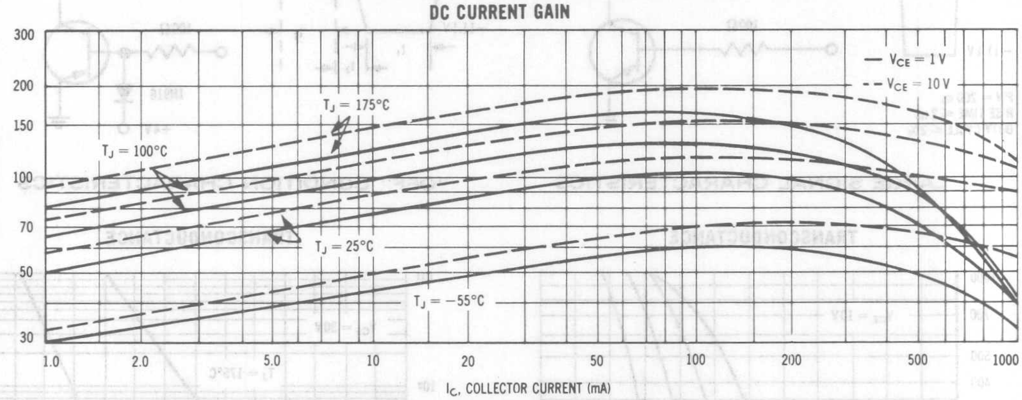
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	15	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	80	pF
Current Gain — High Frequency (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	2N3762, 2N3764 2N3763, 2N3765	$\|h_{fe}\|$	1.8 1.5	— —	—
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 30 V, $V_{BE(off)}$ = 2.0 V, I_C = 1.0 Amp, I_{B1} = 100 mA)	t_d	—	8.0	ns
Rise Time		t_r	—	3.5	ns
Storage Time	(V_{CC} = 30 V, I_C = 1.0 Amp, I_{B1} = $-I_{B2}$ = 100 mA)	t_s	—	80	ns
Fall Time		t_f	—	35	ns
Total Control Charge (I_C = 1.0 Amp, I_B = 100 mA, V_{CC} = 30 V)		Q_T	—	30	pC

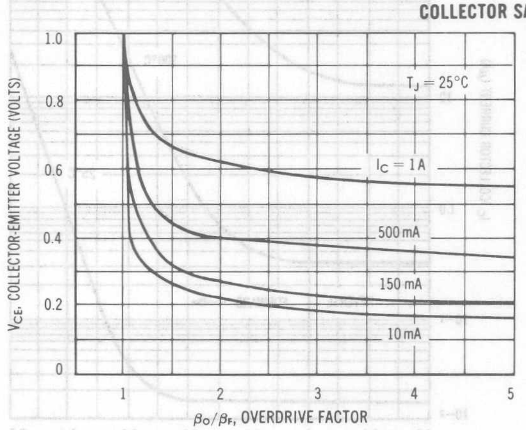
(1) Pulse Test: PW ≤ 300 μs, Duty Cycle ≤ 2.0%.

"ON" CONDITION CHARACTERISTICS

DC CURRENT GAIN



COLLECTOR SATURATION REGION

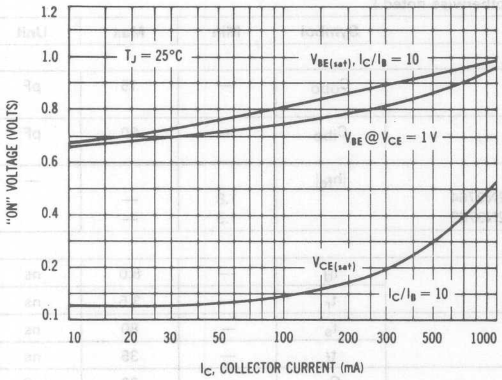


This graph shows the effect of base current on collector current. β_O (current gain at the edge of saturation) is the current gain of the transistor at 1 volt, and β_F (forced gain) is the ratio of I_C/I_{BF} in a circuit. EXAMPLE: For type 2N3734, estimate a base current (I_{BF}) to ensure saturation at a temperature of 25°C and a collector of 500 mA.

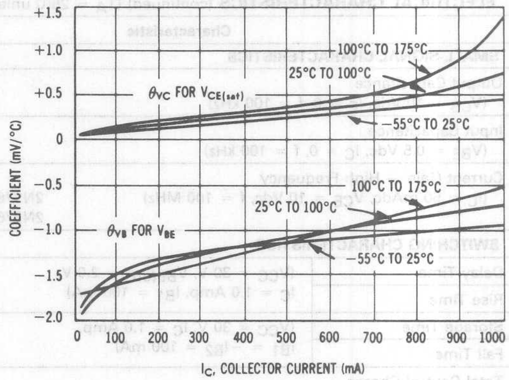
Observe that at I_C = 500 mA an overdrive factor of at least 2.0 is required to drive the transistor well into the saturation region. From Figure 1, it is seen that h_{FE} @ 1 volt is typically 54 (guaranteed limits from the Table of Characteristics can be used for "worst-case" design).

$$\frac{\beta_O}{\beta_F} = \frac{h_{FE}@\,1\,\text{Volt}}{I_C/I_{BF}} \qquad 2 = \frac{54}{500\,\text{mA}/I_{BF}} \qquad I_{BF} \approx 18.5\,\text{mA typ}$$

"ON" VOLTAGES

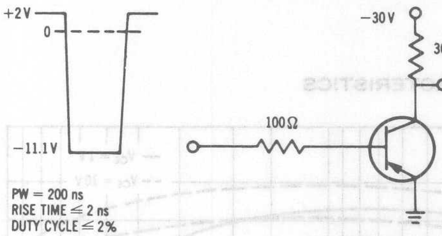


TEMPERATURE COEFFICIENTS

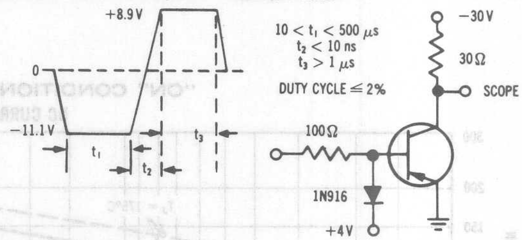


SWITCHING TIME EQUIVALENT TEST CIRCUITS

TURN-ON TIME

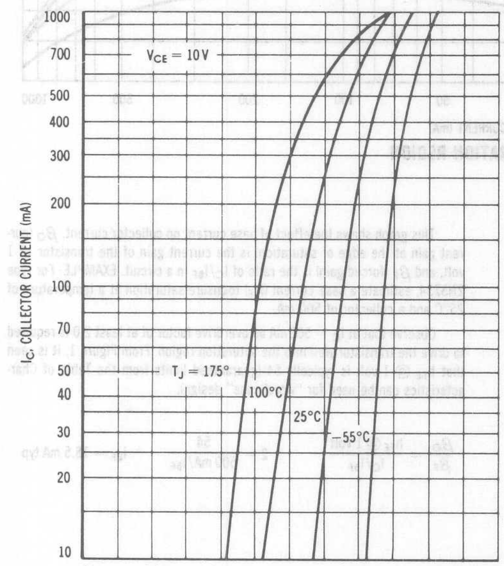


TURN-OFF TIME



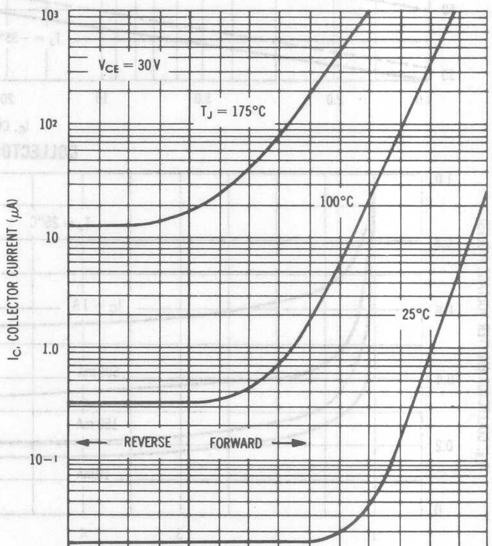
LARGE SIGNAL CHARACTERISTICS

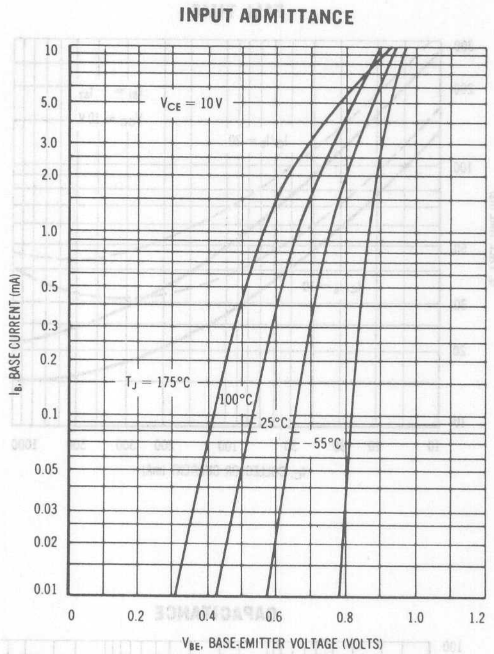
TRANSCONDUCTANCE

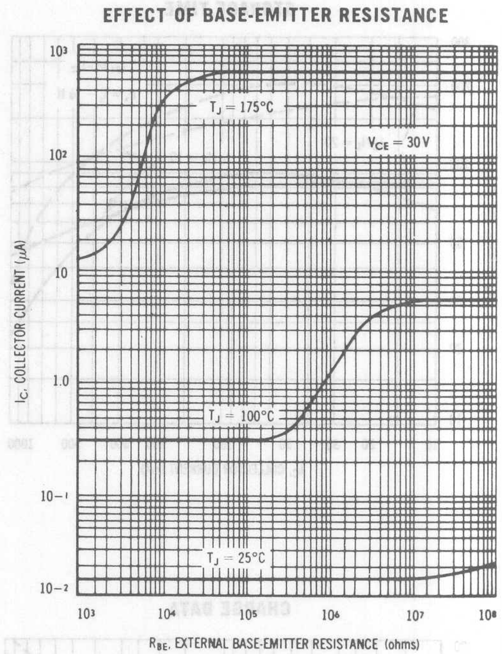


"OFF" CONDITION CHARACTERISTICS

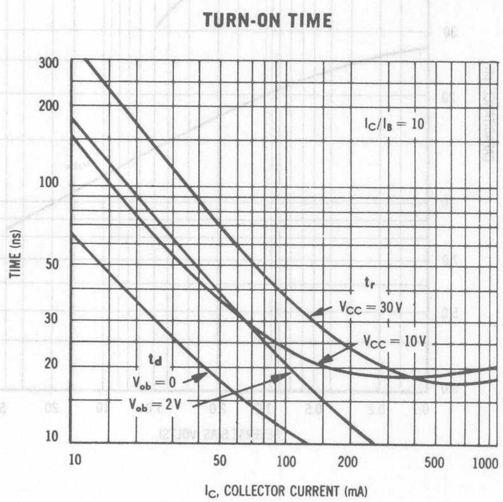
TRANSCONDUCTANCE

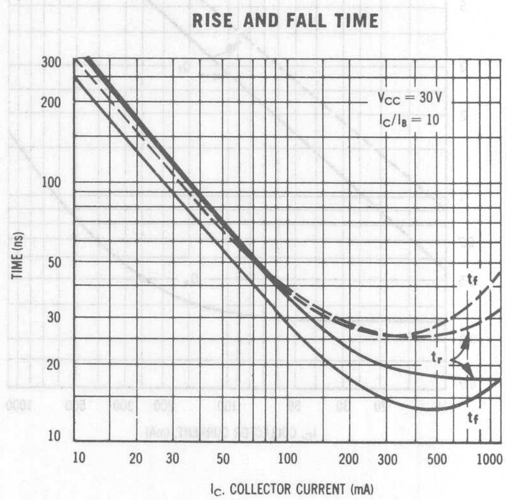




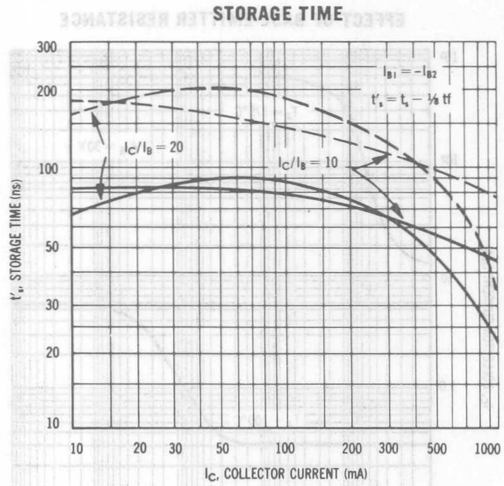


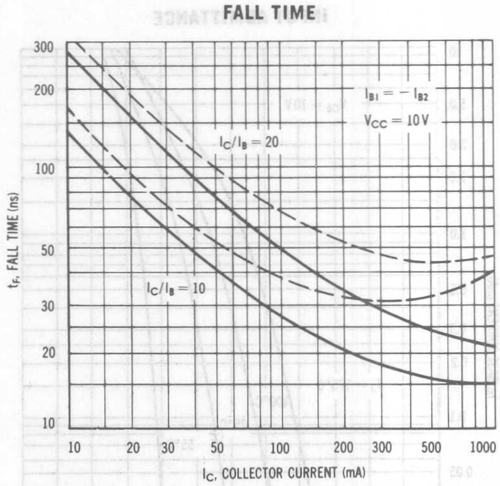
— T_J = 25°C SWITCHING CHARACTERISTICS - - T_J = 150°C

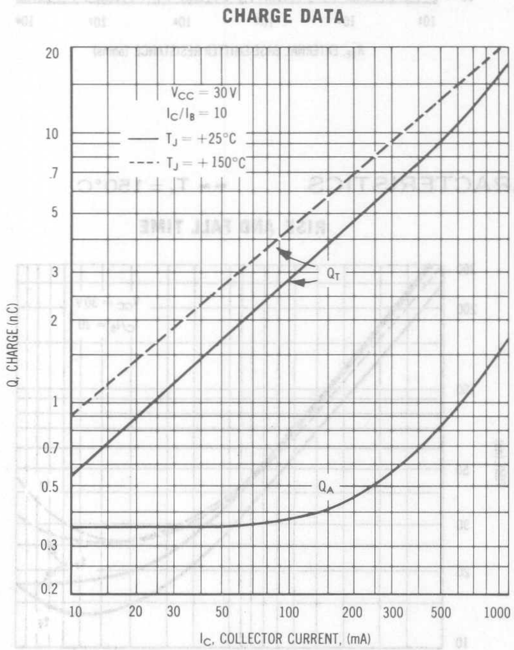


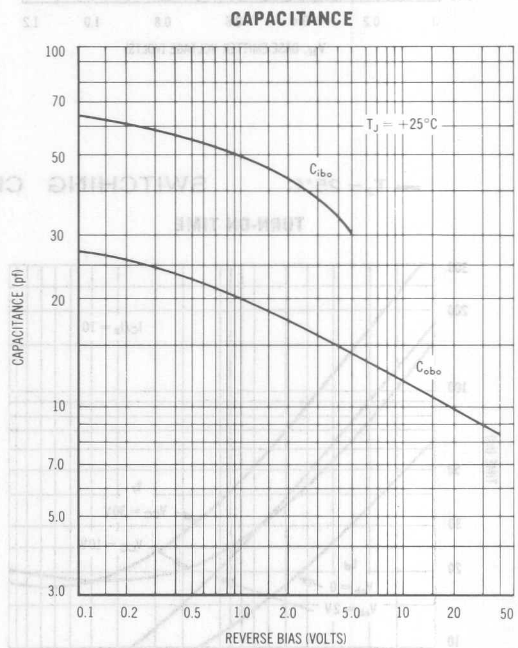


4

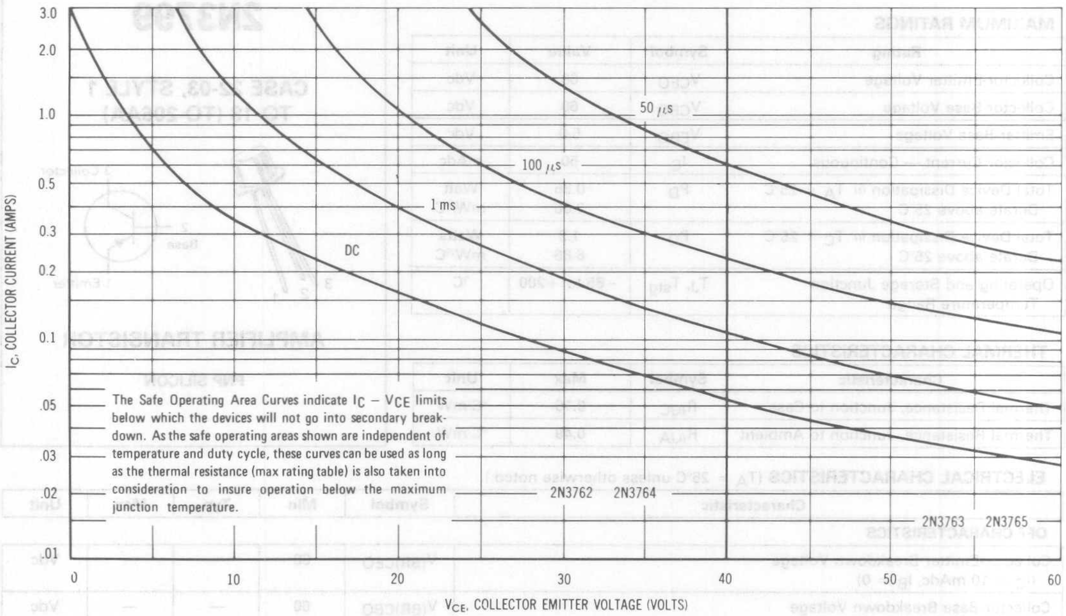

STORAGE TIME
$I_{B1} = -I_{B2}$
$t'_s = t_s - 1/8\ t_f$
$I_C/I_B = 20$
$I_C/I_B = 10$
t'_s, STORAGE TIME (ns)
I_C, COLLECTOR CURRENT (mA)


FALL TIME
$I_{B1} = -I_{B2}$
$V_{CC} = 10\ V$
$I_C/I_B = 20$
$I_C/I_B = 10$
t_f, FALL TIME (ns)
I_C, COLLECTOR CURRENT (mA)


CHARGE DATA
$V_{CC} = 30\ V$
$I_C/I_B = 10$
$T_J = +25°C$
$T_J = +150°C$
Q_T
Q_A
Q, CHARGE (nC)
I_C, COLLECTOR CURRENT, (mA)


CAPACITANCE
$T_J = +25°C$
C_{ibo}
C_{obo}
CAPACITANCE (pf)
REVERSE BIAS (VOLTS)

ACTIVE REGION SAFE OPERATING AREAS



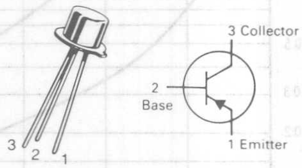
4

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	60	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	50	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.36 2.06	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.2 6.86	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

2N3799

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



AMPLIFIER TRANSISTOR

PNP SILICON

4

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.15	°C/mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	0.49	°C/mW

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage ($I_C = 10$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	60	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)		$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$) ($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = 150°C$)		I_{CBO}	 — —	 — —	 0.01 10	μAdc
Emitter Cutoff Current ($V_{BE} = 4.0$ Vdc, $I_C = 0$)		I_{EBO}	—	—	20	nAdc
ON CHARACTERISTICS						
DC Current Gain(1) ($I_C = 1.0$ μAdc, $V_{CE} = 5.0$ Vdc)	 2N3799	h_{FE}	 75	 —	 —	—
($I_C = 10$ μAdc, $V_{CE} = 5.0$ Vdc)	2N3798 2N3799		100 225	— —	— —	
($I_C = 100$ μAdc, $V_{CE} = 5.0$ Vdc)	2N3798 2N3799		150 300	— —	— —	
($I_C = 100$ μAdc, $V_{CE} = 5.0$ Vdc, $T_A = -55°C$)	2N3798 2N3799		75 150	— —	— —	
($I_C = 500$ μAdc, $V_{CE} = 5.0$ Vdc)	2N3798 2N3799		150 300	— —	450 900	
($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc)	2N3798 2N3799		150 300	— —	— —	
($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc)	2N3798 2N3799		125 250	— —	— —	
Collector-Emitter Saturation Voltage(1) ($I_C = 100$ μAdc, $I_B = 10$ μAdc) ($I_C = 1.0$ mAdc, $I_B = 100$ μAdc)		$V_{CE(sat)}$	 — —	 — —	 0.2 0.25	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 100$ μAdc, $I_B = 10$ μAdc) ($I_C = 1.0$ mAdc, $I_B = 100$ μAdc)		$V_{BE(sat)}$	 — —	 — —	 0.7 0.8	Vdc
Base-Emitter On Voltage ($I_C = 100$ μAdc, $V_{CE} = 5.0$ Vdc)		$V_{BE(on)}$	—	—	0.7	Vdc

Characteristic		Symbol	Min	Typ	Max	Unit
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product(2)		f_T				MHz
(I_C = 500 μAdc, V_{CE} = 5.0 Vdc, f = 30 MHz)			30	—	—	
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)			100	—	500	
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	—	4.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	—	8.0	pF
Input Impedance		h_{ie}				k ohms
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3798		3.0	—	15	
	2N3799		10	—	40	
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{re}	—	—	25	X 10^{-4}
Small-Signal Current Gain		h_{fe}				—
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3798		150	—	600	
	2N3799		300	—	900	
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{oe}	5.0	—	60	μmhos
Noise Figure (I_C = 100 μAdc, V_{CE} = 10 Vdc, R_G = 3.0 k ohms),		NF				dB
Spot Noise f = 100 Hz, B.W. = 20 Hz	2N3798		—	4.0	7.0	
	2N3799		—	2.5	4.0	
f = 1.0 kHz, B.W. = 200 Hz	2N3798		—	1.5	3.0	
	2N3799		—	0.8	1.5	
f = 10 kHz, B.W. = 2.0 kHz	2N3798		—	1.0	2.5	
	2N3799		—	0.8	1.5	
Broadband Noise-Bandwidth 10 Hz to 15.7 kHz	2N3798		—	2.5	3.5	
	2N3799		—	1.5	2.5	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

SPOT NOISE FIGURE
(V_{CE} = 10 Vdc, T_A = 25°C)

FIGURE 1 — SOURCE RESISTANCE EFFECTS, f = 1.0 kHz

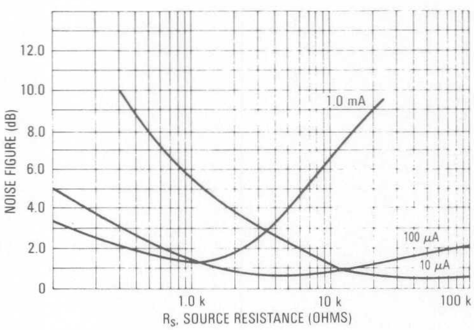


FIGURE 2 — SOURCE RESISTANCE EFFECTS, f = 10 Hz

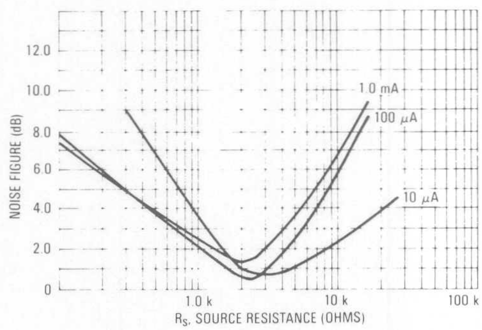


FIGURE 3 — FREQUENCY EFFECTS

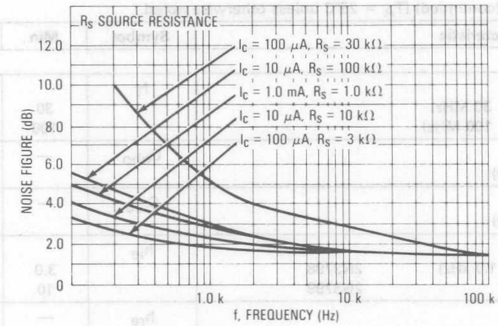


FIGURE 4a — TYPICAL CURRENT GAIN CHARACTERISTICS—2N3798

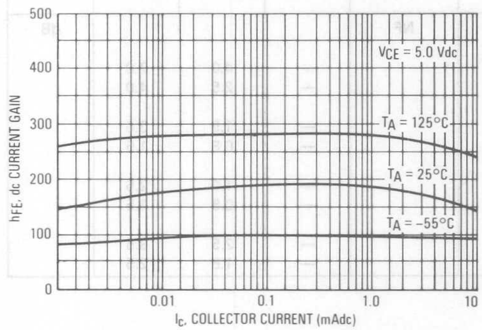
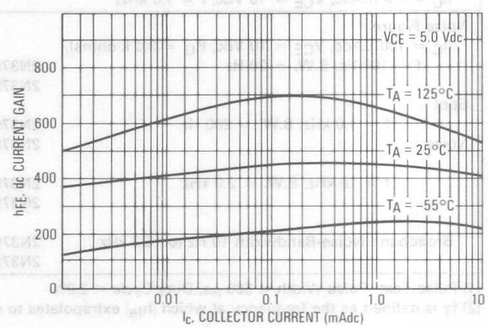


FIGURE 4b — TYPICAL CURRENT GAIN CHARACTERISTICS — 2N3799



MAXIMUM RATINGS

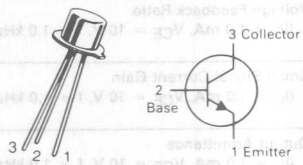
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.36 2.06	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.2 6.9	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.15	°C/mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	0.49	°C/mW

2N3946
2N3947

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc)		$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current (V_{CE} = 40 Vdc, V_{OB} = 3.0 Vdc) (V_{CE} = 40 Vdc, V_{OB} = 3.0 Vdc, T_A = 150°C)		I_{CEX}	 — —	 0.010 15	μAdc
Base Cutoff Current (V_{CE} = 40 Vdc, V_{OB} = 3.0 Vdc)		I_{BL}	—	.025	μAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc)	 2N3946 2N3947	h_{FE}	 30 60	 — —	—
(I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc)	2N3946 2N3947		45 90	— —	
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	2N3946 2N3947		50 100	150 300	
(I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	2N3946 2N3947		20 40	— —	
Collector-Emitter Saturation Voltage(1) (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{CE(sat)}$	 — —	 0.2 0.3	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{BE(sat)}$	 0.6 —	 0.9 1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	 2N3946 2N3947	f_T	 250 300	 — —	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	4.0	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Input Capacitance (V_{BE} = 1.0 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	8.0	pF
Input Impedance (I_C = 1.0 mA, V_{CE} = 10 V, f = 1.0 kHz)	2N3946 2N3947	h_{ie}	0.5 2.0	6.0 12	kohms
Voltage Feedback Ratio (I_C = 1.0 mA, V_{CE} = 10 V, f = 1.0 kHz)	2N3946 2N3947	h_{re}	— —	10 20	X 10^{-4}
Small Signal Current Gain (I_C = 1.0 mA, V_{CE} = 10 V, f = 1.0 kHz)	2N3946 2N3947	h_{fe}	50 100	250 700	—
Output Admittance (I_C = 1.0 mA, V_{CE} = 10 V, f = 1.0 kHz)	2N3946 2N3947	h_{oe}	1.0 5.0	30 50	µmhos
Collector Base Time Constant (I_C = 10 mA, V_{CE} = 20 V, f = 31.8 MHz)		$rb'C_C$	—	200	ps
Noise Figure (I_C = 100 µA, V_{CE} = 5.0 V, R_g = 1.0 kΩ, f = 10 Hz to 15.7 kHz)		NF	—	5.0	dB

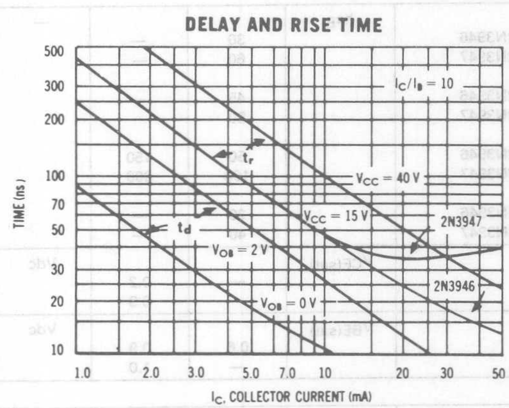
SWITCHING CHARACTERISTICS

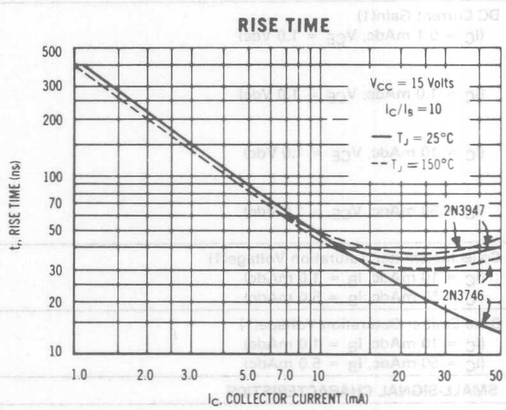
			Symbol	Min	Max	Unit
Delay Time	V_{CC} = 3.0 Vdc, V_{OB} = 0.5 Vdc,		t_d	—	35	ns
Rise Time	I_C = 10 mAdc, I_{B1} = 1.0 mA		t_r	—	35	ns
Storage Time	V_{CC} = 3.0 V, I_C = 10 mA,	2N3946 2N3947	t_s	—	300 375	ns
Fall Time	I_{B1} = I_{B2} = 1.0 mAdc		t_f	—	75	ns

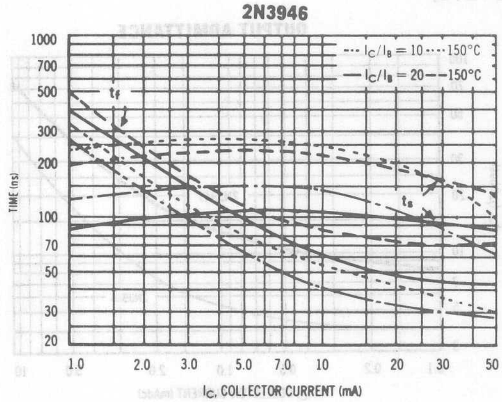
(1) Pulse Test: PW ≤ 300 µs, Duty Cycle ≤ 2%.

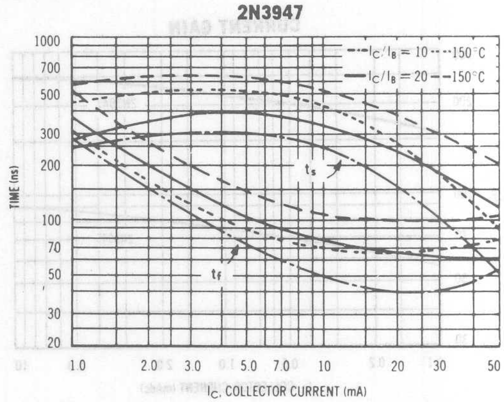
TYPICAL SWITCHING CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

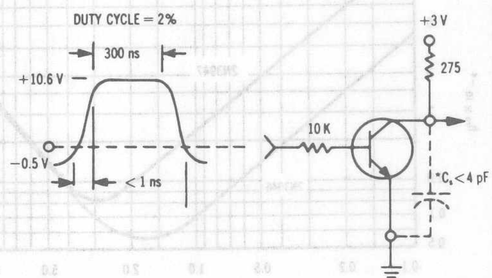




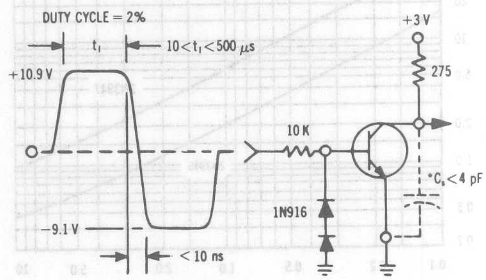




TURN-ON TIME EQUIVALENT TEST CIRCUIT



TURN-OFF TIME EQUIVALENT TEST CIRCUIT

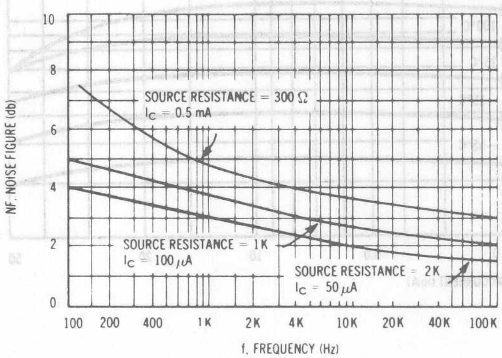


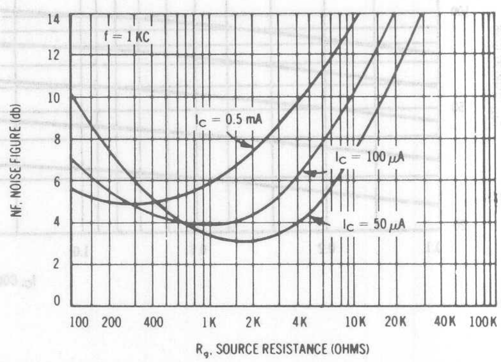
*TOTAL SHUNT CAPACITANCE OF TEST JIG AND CONNECTORS

AUDIO SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE VARIATIONS

V_{CE} = 5 V, T_A = 25°C



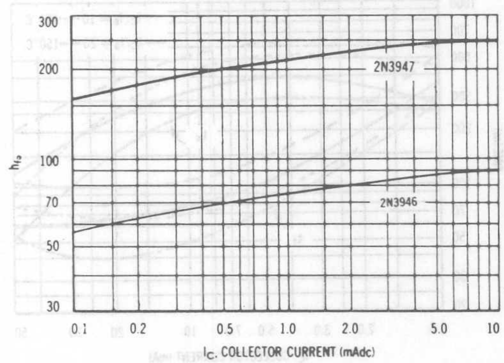


4

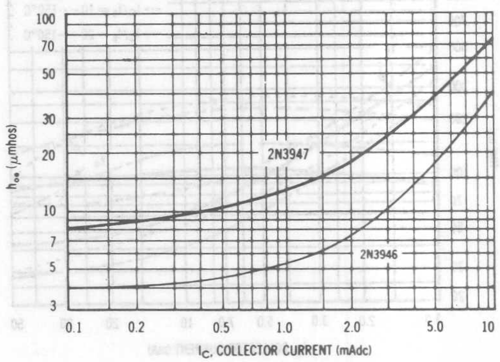
h PARAMETERS

$V_{CE} = 10$ V, $T_A = 25°$C, f = 1 Kc

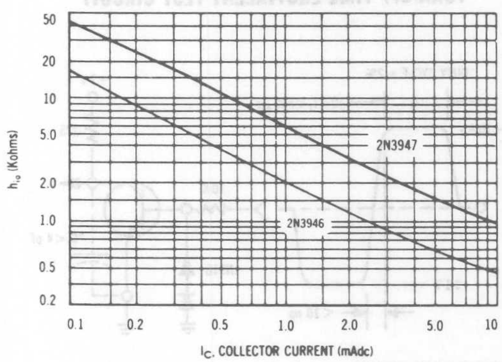
CURRENT GAIN



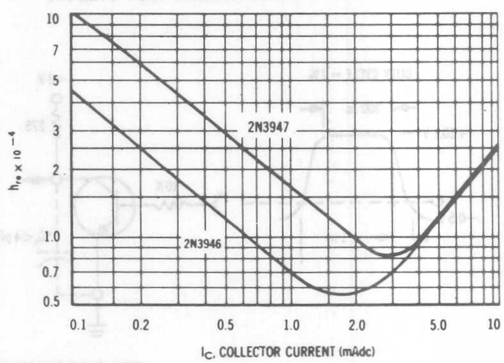
OUTPUT ADMITTANCE



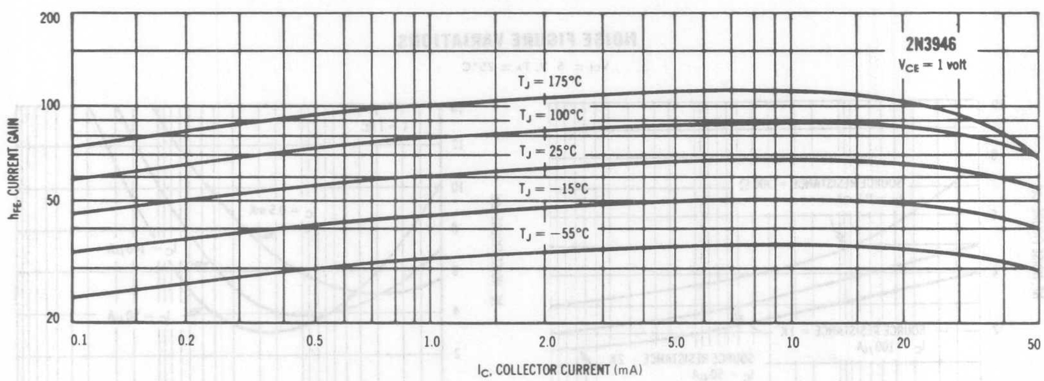
INPUT IMPEDANCE

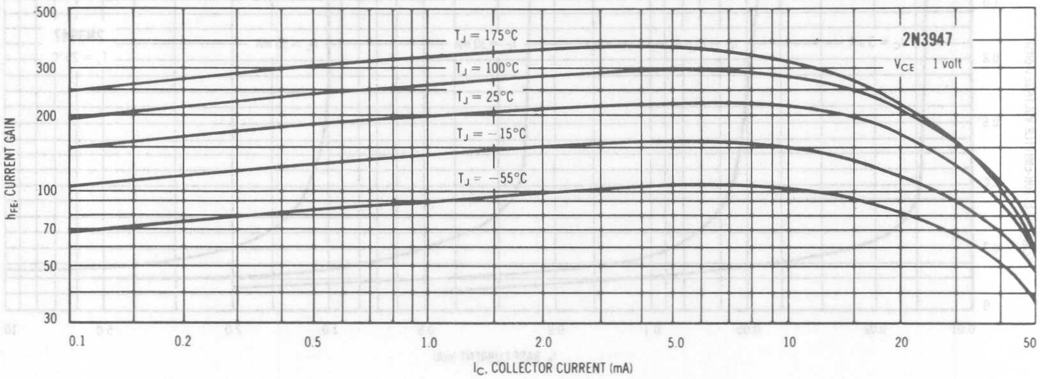


VOLTAGE FEEDBACK RATIO

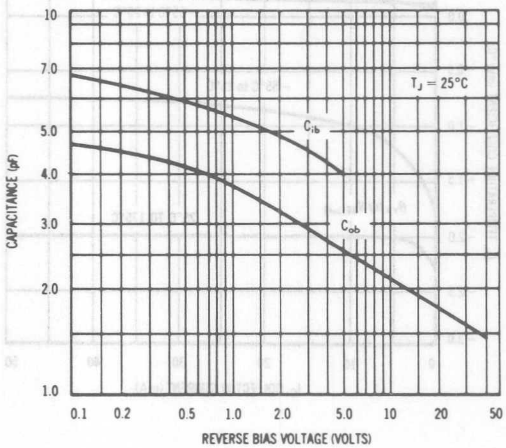


CURRENT GAIN CHARACTERISTICS

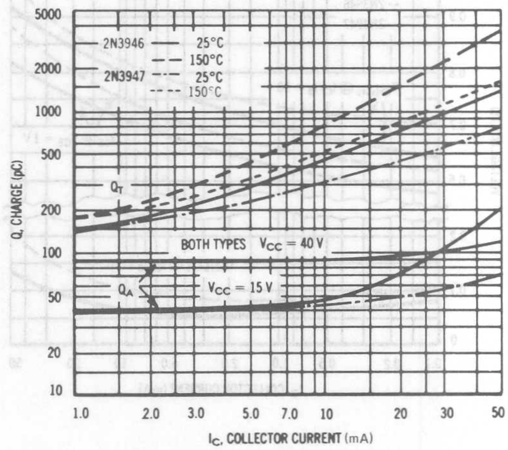




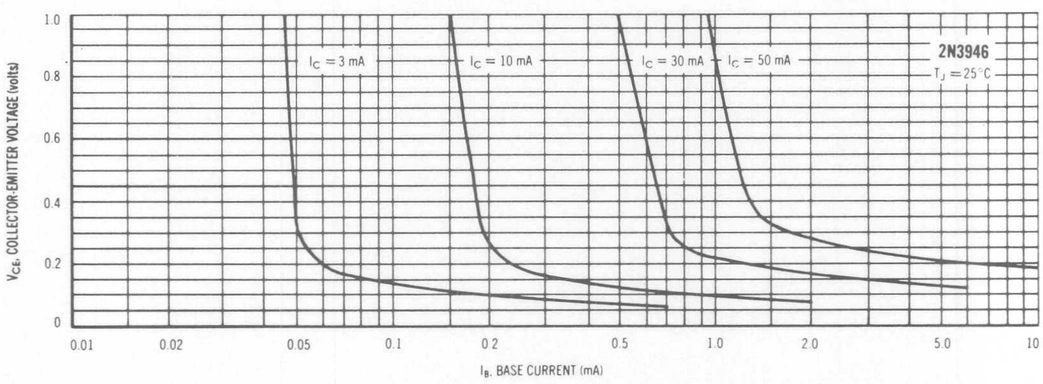
CAPACITANCE



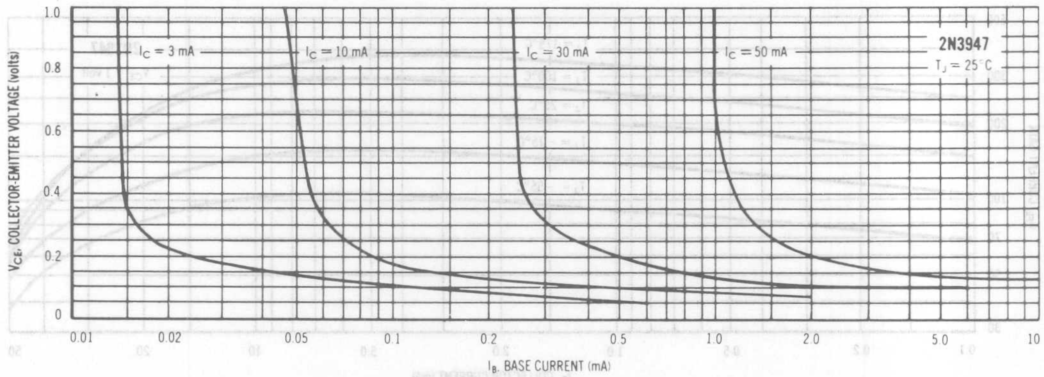
CHARGE DATA



COLLECTOR SATURATION REGION

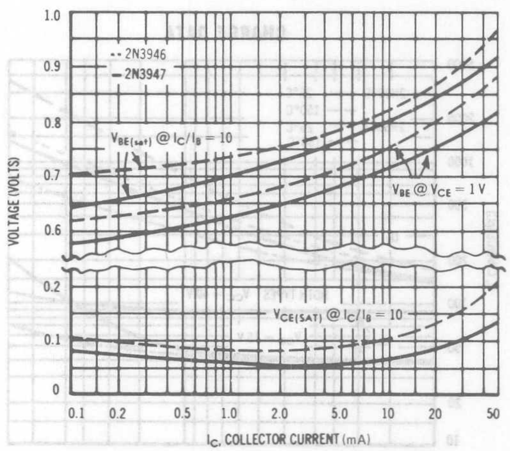


4

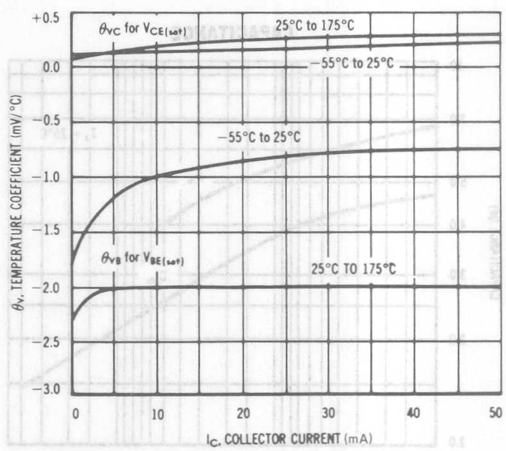


4

"ON" VOLTAGES

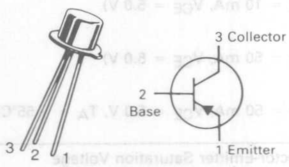


TEMPERATURE COEFFICIENTS



2N3965

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



AMPLIFIER TRANSISTOR

PNP SILICON

Refer to 2N3798 for graphs.

MAXIMUM RATINGS

Rating	Symbol	2N3962 2N3965	2N3964	2N3963	Unit
Collector-Emitter Voltage	V_{CEO}	60	45	80	V
Collector-Base Voltage	V_{CBO}	60	45	80	V
Emitter-Base Voltage	V_{EBO}		6.0		V
Collector Current — Continuous	I_C		200		mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D		0.36 2.06		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D		1.2 6.85		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−65 to +200		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 5.0$ mA)	2N3962, 2N3965 2N3963 2N3964	$V_{(BR)CEO}$	60 80 45	— 	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 10\ \mu A$)	2N3962, 2N3965 2N3963 2N3964	$V_{(BR)CES}$	60 80 45	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu A$)	2N3962, 2N3965 2N3963 2N3964	$V_{(BR)CBO}$	60 80 45	— —	Vdc
Emitter-Base Breakdown Voltage ($I_C = 10\ \mu A$)		$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 50$ V; 2N3964 = 40 V) ($V_{CE} = 70$ V)	 2N3965, 2N3962 2N3963	I_{CBO}	 — —	 10 10	nAdc
Collector Cutoff Current ($V_{CE} = 50$ V) ($V_{CE} = 70$ V) ($V_{CE} = 40$ V) ($V_{CE} = 50$ V)	 2N3962 2N3963 2N3964 2N3965	I_{CES}	 — — — —	 10 10 10 10	nAdc
Emitter Cutoff Current ($V_{EB} = 4.0$ V)		I_{EBO}	—	10	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) ($I_C = 10\ \mu A$, $V_{CE} = 5.0$ V)	 2N3962, 2N3963 2N3964, 2N3965	h_{FE}	 100 250	 300 500	—
($I_C = 100\ \mu A$, $V_{CE} = 5.0$ V)	2N3962, 2N3963 2N3964, 2N3965		100 250	— —	
($I_C = 1.0$ mA, $V_{CE} = 5.0$)	2N3962, 2N3963 2N3964, 2N3965		100 250	450 600	
($I_C = 10\ \mu A$, $V_{CE} = 5.0$, $T_A = -55°C$)	2N3962, 2N3963 2N3964, 2N3965		40 100	— —	

(continued)

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
DC Current Gain(1) continued					
(I_C = 1.0 mA, V_{CE} = 5.0 V, T_A = 100°C)	2N3962, 2N3963		—	600	
	2N3964, 2N3965		—	800	
(I_C = 1.0 μA, V_{CE} = 5.0 V)	2N3962, 2N3963		60	—	
	2N3964, 2N3965		180	—	
(I_C = 10 mA, V_{CE} = 5.0 V)	2N3962, 2N3963		100	—	
	2N3964, 2N3965		200	—	
(I_C = 50 mA, V_{CE} = 5.0 V)	2N3962, 2N3963		90	—	
	2N3964, 2N3965		180	—	
(I_C = 50 mA, V_{CE} = 5.0 V, T_A = −55°C)	2N3962, 2N3963		45		
	2N3964, 2N3965		90		
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$			
(I_C = 10 mA, I_B = 0.5 mA)			—	0.25	V
(I_C = 50 mA, I_B = 5.0 mA)(1)			—	0.4	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$			
(I_C = 10 mA, I_B = 0.5 mA)			—	0.9	V
(I_C = 50 mA, I_B = 5.0 mA)(1)			—	0.95	V

SMALL-SIGNAL CHARACTERISTICS

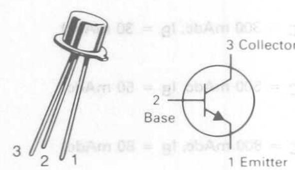
Characteristic		Symbol	Min	Max	Unit
Output Capacitance (V_{CB} = 5.0 V, f = 1.0 MHz)		C_{obo}	—	6.0	pF
Input Capacitance (V_{EB} = 0.5 V, f = 1.0 MHz)		C_{ibo}	—	15	pF
Input Impedance		h_{ie}			kΩ
(I_C = 1.0 mA, V_{CE} = 5.0 V, f = 1.0 kHz)	2N3962, 2N3963		2.5	17	
	2N3964, 2N3965		6.0	20	
Voltage Feedback Ratio (I_C = 1.0 mA, V_{CE} = 5.0, f = 1.0 kHz)		h_{re}	—	10	10^{-4}
Small-Signal Current Gain		h_{fe}			
(I_C = 1.0 mA, V_{CE} = 5.0 V, f = 1.0 kHz)	2N3962, 2N3963		100	550	—
	2N3964, 2N3965		250	700	—
Magnitude of Forward Current Transfer Ratio, Common-Emitter		$\|h_{fe}\|$			
(I_C = 0.5 mA, V_{CE} = 5.0 V, f = 20 MHz)	2N3962, 2N3963		2.0	8.0	—
	2N3964, 2N3965		2.5	8.0	—
Output Admittance		h_{oe}			μmhos
(I_C = 1.0 mA, V_{CE} = 5.0, f = 1.0 kHz)	2N3962, 2N3963		5.0	40	
	2N3964, 2N3965		5.0	50	
Noise Figure		NF			dB
(I_C = 20 mA, V_{CE} = 5.0 V, BW = 15.7 kHz)	2N3962, 2N3963		—	3	
	2N3964, 2N3965		—	2	
(I_C = 20 μA, V_{CE} = 5.0 V, BW = 1.5 kHz, f = 10 kHz, R_S = 10 kΩ)	2N3962, 2N3963		—	3	
	2N3964, 2N3965		—	2	
(I_C = 20 μA, V_{CE} = 5.0 V, BW = 150 Hz, f = 1.0 kHz, R_S = 10 kΩ)	2N3962, 2N3963		—	3	
	2N3964, 2N3965		—	2	
(I_C = 20 μA, V_{CE} = 5.0 V, BW = 15 Hz, f = 100 Hz, R_S = 10 kΩ)	2N3962, 2N3963		—	10	
	2N3964, 2N3965		—	4	
(I_C = 20 μA, V_{CE} = 5.0 V, BW = 2.0 Hz, f = 10 Hz, R_S = 10 kΩ)	2N3964, 2N3965		—	8	

(1) Pulse Test: PW ≤ 300 μs, Duty Cycle ≤ 2%.

4

2N4013
2N4014

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

NPN SILICON

4

MAXIMUM RATINGS

Rating	Symbol	2N4013	2N4014	Unit
Collector-Emitter Voltage	V_{CEO}	30	50	Vdc
Collector-Base Voltage	V_{CBO}	50	80	Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous — Peak	I_C	1.0 2.0		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.5 28.6		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.4 6.8		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(1)		$V_{(BR)CEO}$				Vdc
(I_C = 10 mAdc, I_B = 0)	2N4014		50	—	—	
	2N4013		30	—	—	
Collector-Emitter Breakdown Voltage		$V_{(BR)CES}$				Vdc
(I_C = 10 μAdc, V_{BE} = 0)	2N4014		80	—	—	
	2N4013		50	—	—	
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$				Vdc
(I_C = 10 μAdc, I_E = 0)	2N4014		80	—	—	
	2N4013		50	—	—	
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	6.0	—	—	Vdc
Collector Cutoff Current		I_{CBO}				μAdc
(V_{CB} = 60 Vdc, I_E = 0)	2N4014			0.12	1.7	
(V_{CB} = 40 Vdc, I_E = 0)	2N4013		—	0.12	1.7	
(V_{CB} = 60 Vdc, I_E = 0, T_A = 100°C)	2N4014				120	
(V_{CB} = 40 Vdc, I_E = 0, T_A = 100°C)	2N4013		—	—	120	
Collector Cutoff Current		I_{CES}				μAdc
(V_{CE} = 80 Vdc, V_{EB} = 0)	2N4014		—	0.15	10	
(V_{CE} = 50 Vdc, V_{EB} = 0)	2N4013		—	0.15	10	
ON CHARACTERISTICS(1)						
DC Current Gain		h_{FE}				—
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)			30	—	—	
(I_C = 100 mAdc, V_{CE} = 1.0 Vdc)			60	—	150	
(I_C = 100 mAdc, V_{CE} = 1.0 Vdc, T_A = −55°C)			30	—	—	
(I_C = 300 mAdc, V_{CE} = 1.0 Vdc)			40	—	—	
(I_C = 500 mAdc, V_{CE} = 1.0 Vdc)			35	—	—	
(I_C = 500 mAdc, V_{CE} = 1.0 Vdc, T_A = −55°C)			20	—	—	
(I_C = 800 mAdc, V_{CE} = 2.0 Vdc)	2N4014		20			
	2N4013		25	—	—	
(I_C = 1.0 Adc, V_{CE} = 5.0 Vdc)	2N4014		25			
	2N4013		30	—	—	

(continued)

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

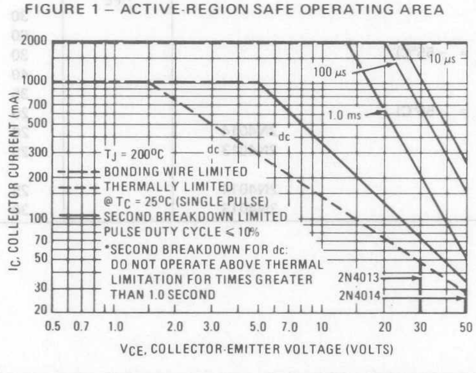
Characteristic		Symbol	Min	Typ	Max	Unit
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$				Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)	2N4014		—	0.17	0.25	
	2N4013		—	0.17	0.25	
(I_C = 100 mAdc, I_B = 10 mAdc)	2N4014		—	0.19	0.26	
	2N4013		—	0.19	0.20	
(I_C = 300 mAdc, I_B = 30 mAdc)	2N4014		—	0.25	0.40	
	2N4013		—	0.25	0.32	
(I_C = 500 mAdc, I_B = 50 mAdc)	2N4014		—	0.30	0.52	
	2N4013		—	0.30	0.42	
(I_C = 800 mAdc, I_B = 80 mAdc)	2N4014		—	0.43	0.80	
	2N4013		—	0.43	0.65	
(I_C = 1.0 Adc, I_B = 100 mAdc)	2N4014		—	0.55	0.95	
	2N4013		—	0.55	0.75	
Base-Emitter Saturation Voltage		$V_{BE(sat)}$				Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)			—	—	0.76	
(I_C = 100 mAdc, I_B = 10 mAdc)			—	—	0.86	
(I_C = 300 mAdc, I_B = 30 mAdc)			—	—	1.1	
(I_C = 500 mAdc, I_B = 50 mAdc)			0.8	—	1.1	
(I_C = 800 mAdc, I_B = 80 mAdc)			—	—	1.5	
(I_C = 1.0 Adc, I_B = 100 mAdc)			—	—	1.7	
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product(2) (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	300	—	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	2N4014	C_{obo}	—	—	10	pF
	2N4013		—	—	12	
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	—	55	pF

SWITCHING CHARACTERISTICS

Characteristic	Conditions		Symbol	Min	Typ	Max	Unit
Delay Time	(V_{CC} = 30 Vdc, $V_{BE(off)}$ = 3.8 Vdc, I_C = 500 mAdc, I_{B1} = 50 mAdc) (Figures 8, 10)		t_d	—	5.0	10	ns
Rise Time			t_r	—	15	30	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 500 mAdc, I_{B1} = I_{B2} = 50 mAdc) (Figures 9, 10)	2N4014	t_s	—	30	50	ns
Fall Time		2N4013	t_f	—	20	25	ns
					25	30	
Turn-On Time	(V_{CC} = 30 Vdc, $V_{BE(off)}$ = 3.8 Vdc, I_C = 500 mAdc, I_{B1} = 50 mAdc) (Figures 8, 10)		t_{on}	—	20	35	ns
Turn-Off Time	(V_{CC} = 30 Vdc, I_C = 500 mAdc, I_{B1} = I_{B2} = 50 mAdc) (Figures 9, 10)	2N4014 2N4013	t_{off}	—	50	60	ns

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 1.0%.
(2) $f_T = |h_{fe}| \cdot f_{test}$.

FIGURE 1 – ACTIVE-REGION SAFE OPERATING AREA



TYPICAL DC CHARACTERISTICS

FIGURE 2 – DC CURRENT GAIN

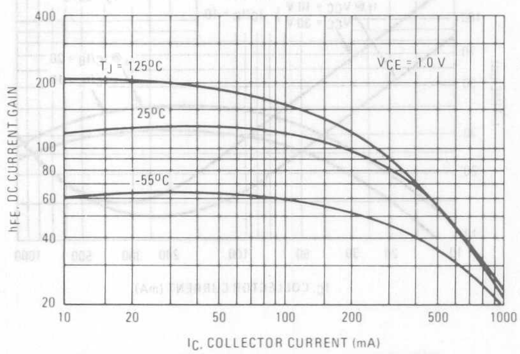


FIGURE 3 – "ON" VOLTAGES

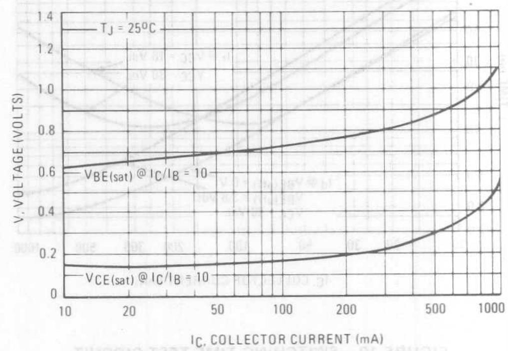


FIGURE 4 – COLLECTOR SATURATION REGION

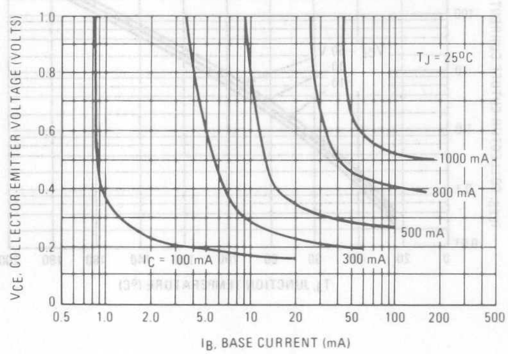
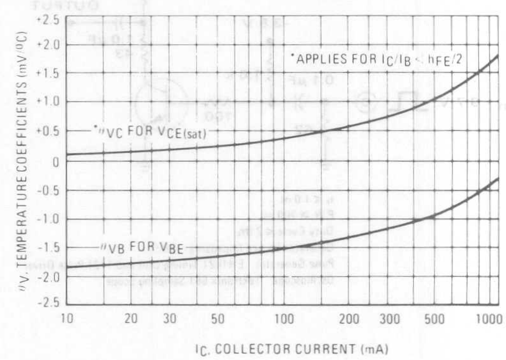


FIGURE 5 – TEMPERATURE COEFFICIENTS



TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 6 – CURRENT-GAIN – BANDWIDTH PRODUCT

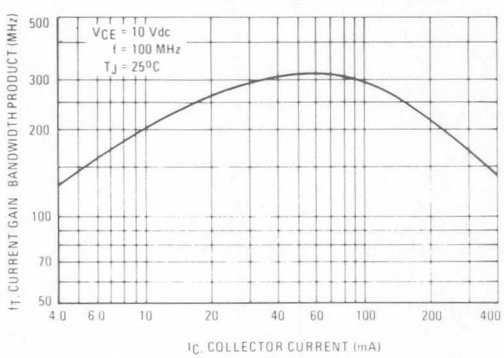


FIGURE 7 – CAPACITANCE

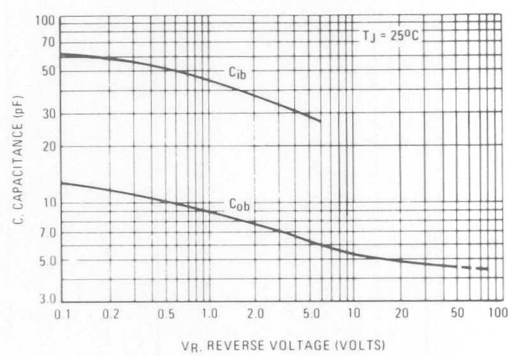


FIGURE 8 – TURN-ON TIME

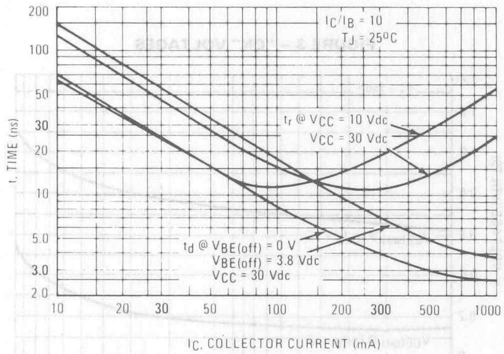


FIGURE 9 – TURN-OFF TIME

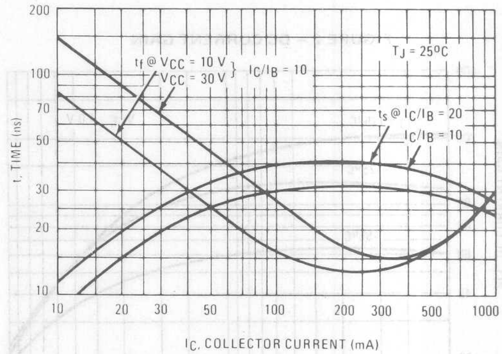
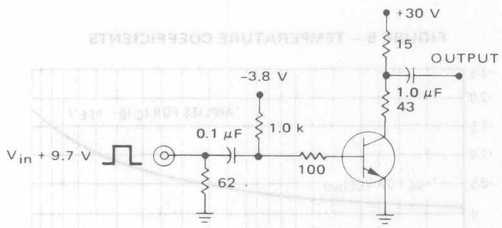
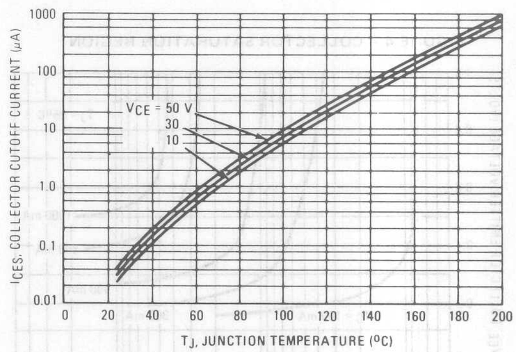


FIGURE 10 – SWITCHING TIME TEST CIRCUIT



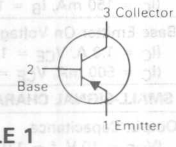
$t_r \leq 1.0$ ns
P.W. $\geq$ 200 ns
Duty Cycle $\leq$ 2.0%
Generator Source Impedance = 50 Ω
Pulse Generator: EH1421 Timing Unit and 1121 Pulse Driver
Oscilloscope: Tektronix 661 Sampling Scope

FIGURE 11 – COLLECTOR CUTOFF CURRENT



2N4026 thru 2N4029

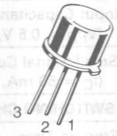
CASE 22-03, STYLE 1
TO-18 (TO-206AA)



2N4030 thru 2N4033

CASE 79-02, STYLE 1
TO-39 (TO-205AD)

JAN, JTX, TXV AVAILABLE IN GENERAL PURPOSE TRANSISTOR



PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	2N4026/28 2N4030/32	2N4027/29 2N4031/33	Unit
Collector-Emitter Voltage(1)	V_{CEO}	60	80	Vdc
Collector-Base Voltage	V_{CBO}	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	5.0	Vdc
		2N4026-2N4029	2N4030-2N4033	
Collector Current — Continuous	I_C	1.0	1.0	Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	.5 2.85	1.25 7.15	W mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	2.0 11.4	7.0 40	W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C
Lead or Terminal Temperature(2)	T_L	+300		°C

(1) Applicable 0 to 10 mA
(2) Measured at a distance not less than 1/16" from seated surface (or case) for 60 Sec.

THERMAL CHARACTERISTICS

Characteristic	Symbol	TO-18	TO-39	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	40	20	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	280	140	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 mA)	 2N4026,28,30,32 2N4027,29,31,33	$V_{(BR)CEO}$	 60 80	 — —	V
Collector-Base Breakdown Voltage (I_C = 10 μA)	 2N4026,28,30,32 2N4027,29,31,33	$V_{(BR)CBO}$	 60 80	 — —	V
Emitter-Base Breakdown Voltage (I_E = 10 μA)		$V_{(BR)EBO}$	5.0	—	V
Collector Cutoff Current (V_{CB} = 50 V) (V_{CB} = 60 V) (V_{CB} = 50 V, T_A = 150°C) (V_{CB} = 60 V, T_A = 150°C)	 2N4026,28,30,32 2N4027,29,31,33 2N4026,28,30,32 2N4027,29,31,33	I_{CBO}	 — — — —	 50 50 50 50	nA μA
Emitter Cutoff Current (V_{EB} = 5.0 V)		I_{EBO}	—	10	μA
ON CHARACTERISTICS					
DC Current Gain (I_C = 100 mA, V_{CE} = 5.0 V, @ −55°C)	 2N4026,27,30,31 2N4028,29,32,33	h_{FE}	 15 40	 — —	—
(I_C = 100 μA, V_{CE} = 5.0 V)	2N4026,27,30,31 2N4028,29,32,33		30 75	— —	
(I_C = 100 mA, V_{CE} = 5.0 V)	2N4026,27,30,31 2N4028,29,32,33		40 100	120 300	
(I_C = 500 mA, V_{CE} = 5.0 V)	2N4026,27,30,31 2N4028,29,32,33		25 70	— —	
(I_C = 1.0 A, V_{CE} = 5.0 V)	2N4026,30 2N4027,31 2N4028,32 2N4029,33		15 10 40 25	— — — —	

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

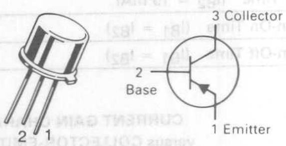
Characteristic		Symbol	Min	Max	Unit
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$			V
(I_C = 150 mA, I_B = 15 mA)			—	0.15	
(I_C = 500 mA, I_B = 50 mA)			—	0.50	
(I_C = 1.0 A, I_B = 100 mA)	2N4026,28,30,32		—	1.0	
Base-Emitter Saturation Voltage (I_C = 150 mA, I_B = 15 mA)		$V_{BE(sat)}$	—	0.9	V
Base-Emitter On Voltage		$V_{BE(on)}$			V
(I_C = 1.0 A, V_{CE} = 1.0 V)	2N4026,28,30,32		—	1.2	
(I_C = 500 mA, V_{CE} = 0.5 V)			—	1.1	
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance (V_{CE} = 10 V, f = 1.0 MHz)		C_{obo}	—	20	pF
Input Capacitance (V_{EB} = 0.5 V, f = 1.0 MHz)		C_{ibo}	—	110	pF
Small Signal Current Gain (I_C = 50 mA, V_{CE} = 10 V, f = 100 MHz)		h_{fe}	1.0	4.0	—
SWITCHING CHARACTERISTICS					
Storage Time (I_C = 500 mA, I_{B1} = I_{B2} = 50 mA)		t_s	—	350	ns
Turn-On Time (I_C = 500 mA, I_{B1} = 50 mA)		t_{on}	—	100	ns
Fall Time (I_C = 500 mA, I_{B1} = I_{B2} = 50 mA)		t_f	—	50	ns

(3) Pulse Width = 300 μs, Duty Cycle 1.0%.

Rating	Symbol	2N4036	2N4037	Unit
Collector-Emitter Voltage	V_{CEO}	65	40 (sus)(1)	Vdc
Collector-Base Voltage	V_{CBO}	90	60	Vdc
Emitter-Base Voltage	V_{EBO}	7.0	7.0	Vdc
Base Current	I_B	0.5		Adc
Collector Current — Continuous	I_C	1.0		Adc
Continuous Power Dissipation at or Below T_C = 25°C Linear Derating Factor	P_D	5.0 28.6	1.0 5.72	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C
Lead Temperature 1/16″ from Case for 10 Seconds	T_L	230		°C

2N4037

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

THERMAL CHARACTERISTICS

Characteristic	Symbol	2N4036	2N4037	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	25	—	°C/W

(1) Must not be tested on a curve tracer.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

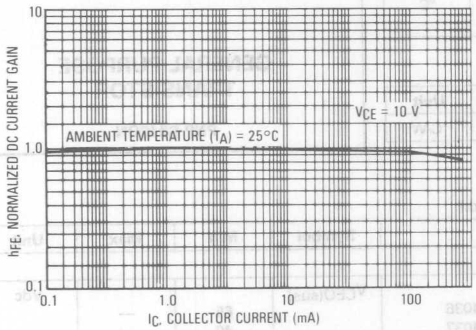
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage (I_C = 100 mAdc, I_B = 0)	2N4036 2N4037	$V_{CEO(sus)}$	65 40	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 0.1 mA dc)	2N4037	$V_{(BR)CBO}$	60	—	Vdc
Collector Cutoff Current (V_{CE} = 85 V, V_{BE} = 1.5 V) (V_{CE} = 30 V, V_{BE} = 1.5 V, T_C = 150°C)	2N4036	I_{CEX}	—	100 0.1	mAdc
Collector Cutoff Current (V_{CB} = 90 V, I_E = 0) (V_{CB} = 60 V, I_E = 0)	2N4036 2N4037	I_{CBO}	—	100 0.25	μAdc
Emitter Cutoff Current (V_{BE} = 7.0 Vdc, I_C = 0) (V_{BE} = 5.0 Vdc, I_C = 0)	2N4036 2N4037	I_{EBO}	— —	10.0 1.0	μAdc
ON CHARACTERISTICS					
DC Current Gain		h_{FE}			—
(I_C = 150 mAdc, V_{CE} = 2.0 V)	2N4036		20	200	
(I_C = 0.1 mAdc, V_{CE} = 10 V)	2N4036		20	—	
(I_C = 1.0 mAdc, V_{CE} = 10 V)	2N4037		15	—	
(I_C = 150 mAdc, V_{CE} = 10 V)	2N4036 2N4037		40 50	140 250	
(I_C = 500 mAdc, V_{CE} = 10 V)	2N4036		20	—	
Collector-Emitter Saturation Voltage (I_C = 150 mA, I_B = 15 mA)	2N4036 2N4037	$V_{CE(sat)}$		0.65 1.4	V
Base-Emitter Saturation Voltage (I_C = 150 mA, I_B = 15 mA)	2N4036	$V_{BE(sat)}$		1.4	V
Base-Emitter On Voltage (I_C = 150 mA, V_{CE} = 10 V)	2N4037	$V_{BE(on)}$		1.5	V
SMALL-SIGNAL CHARACTERISTICS					
Collector-Base Capacitance (V_{CB} = 10 V, f = 1.0 MHz)	2N4037	C_{cb}	—	30	pF
Current Gain — High Frequency (I_C = 50 mA, V_{CE} = 10 V, f = 20 MHz)	2N4036 2N4037	$\|h_{fe}\|$	3.0 3.0	— 10.0	—

4

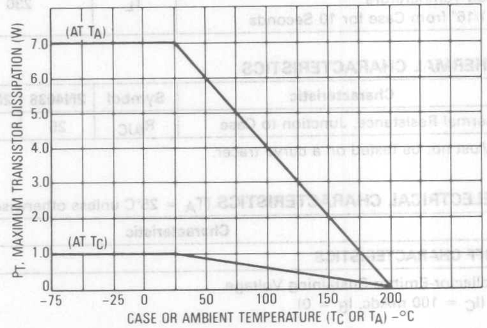
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS					
Rise Time (I_{B1} = 15 mA)	2N4036	t_r	—	70	ns
Storage Time (I_{B2} = 15 mA)	2N4036	t_s	—	600	ns
Fall Time (I_{B2} = 15 mA)	2N4036	t_f	—	100	ns
Turn-On Time (I_{B1} = I_{B2})	2N4036	t_{on}	—	110	ns
Turn-Off Time (I_{B1} = I_{B2})	2N4036	t_{off}	—	700	ns

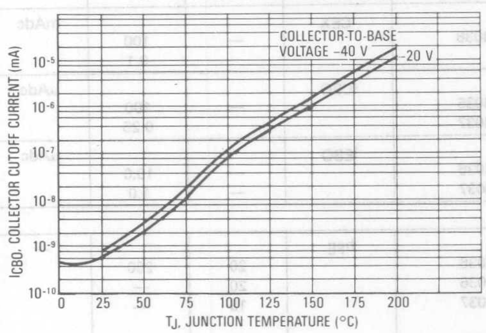
CURRENT GAIN CHARACTERISTICS versus COLLECTOR-EMITTER VOLTAGE



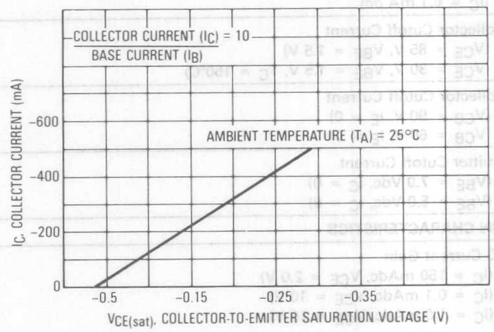
DISSIPATION DERATING CURVE



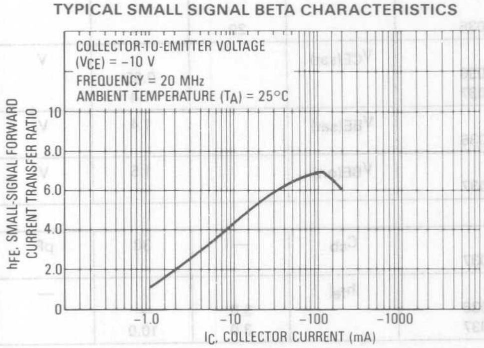
TYPICAL COLLECTOR-CUTOFF CURRENT versus JUNCTION TEMPERATURE



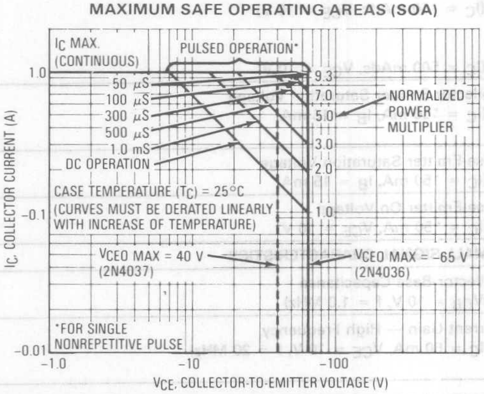
TYPICAL SATURATION-VOLTAGE CHARACTERISTICS



TYPICAL SMALL SIGNAL BETA CHARACTERISTICS

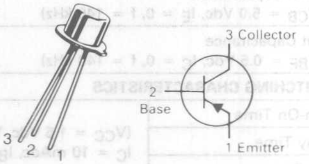


MAXIMUM SAFE OPERATING AREAS (SOA)



2N4208
2N4209

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

PNP SILICON

Refer to MM4257 for graphs.

MAXIMUM RATINGS

Rating	Symbol	2N4208	2N4209	Unit
Collector-Emitter Voltage	V_{CEO}	12	15	Vdc
Collector-Base Voltage	V_{CBO}	12	15	Vdc
Emitter-Base Voltage	V_{EBO}	4.5		Vdc
Collector Current — Continuous	I_C	200		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.36 2.06		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.2 6.9		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(1) ($I_C = 3.0$ mAdc, $I_B = 0$)	2N4208 2N4209	$V_{(BR)CEO}$	12 15	— —	— —	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 100\ \mu$Adc, $V_{BE} = 0$)	2N4208 2N4209	$V_{(BR)CES}$	12 15	— —	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	2N4208 2N4209	$V_{(BR)CBO}$	12 15	— —	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	4.5	5.9	—	Vdc
Collector Cutoff Current ($V_{CE} = 6.0$ Vdc, $V_{BE} = 0$) ($V_{CE} = 8.0$ Vdc, $V_{BE} = 0$) ($V_{CE} = 6.0$ Vdc, $V_{BE} = 0$, $T_A = 125°C$) ($V_{CE} = 8.0$ Vdc, $V_{BE} = 0$, $T_A = 125°C$)	2N4208 2N4209 2N4208 2N4209	I_{CES}	— — — —	— — — —	10 10 5.0 5.0	nAdc μAdc
Base Current ($V_{CE} = 6.0$ Vdc, $V_{BE} = 0$) ($V_{CE} = 8.0$ Vdc, $V_{BE} = 0$)	2N4208 2N4209	I_B	— —	— —	1.0 1.0	nAdc
ON CHARACTERISTICS						
DC Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 0.5$ Vdc)	 2N4208 2N4209	h_{FE}	 15 35	 — —	 — —	—
($I_C = 10$ mAdc, $V_{CE} = 0.3$ Vdc)	2N4208 2N4209		30 50	— —	120 120	
($I_C = 10$ mAdc, $V_{CE} = 0.3$ Vdc, $T_A = -55°C$)	2N4208 2N4209		12 20	— —	— —	
($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc)(1)	2N4208 2N4209		30 40	— —	— —	
Collector-Emitter Saturation Voltage ($I_C = 1.0$ mAdc, $I_B = 0.1$ mAdc)	 2N4208 2N4209	$V_{CE(sat)}$	 — —	 — —	 0.13 0.15	Vdc
($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	2N4208 2N4209		— —	— —	0.15 0.18	
($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)(1)	2N4208 2N4209		— —	— —	0.5 0.6	
Base-Emitter Saturation Voltage ($I_C = 1.0$ mAdc, $I_B = 0.1$ mAdc) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)(1)		$V_{BE(sat)}$	 — 0.75 —	 0.7 0.86 1.1	 0.8 0.90 1.5	Vdc

4

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

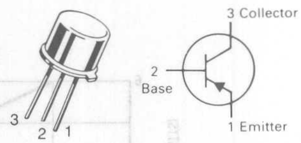
Characteristic			Symbol	Min	Typ	Max	Unit
SMALL-SIGNAL CHARACTERISTICS							
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		2N4208 2N4209	f_T	700 850	1000 1100	— —	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 140 kHz)			C_{obo}	—	2.0	3.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 140 kHz)			C_{ibo}	—	2.0	3.5	pF
SWITCHING CHARACTERISTICS							
Turn-On Time	(V_{CC} = 1.5 Vdc, V_{BE} = 0, I_C = 10 mAdc, I_{B1} = 1.0 mAdc)		t_{on}	—	10	15	ns
Delay Time			t_d	—	5.0	10	ns
Rise Time			t_r	—	5.0	15	ns
Turn-Off Time	(V_{CC} = 1.5 Vdc, I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)	2N4208 2N4209	t_{off}	— —	12 16	15 20	ns
Storage Time		2N4208 2N4209	t_s	— —	12 17	15 20	ns
Fall Time		2N4208 2N4209	t_f	—	6.0 8.0	10 10	ns
Storage Time (I_C ≈ 10 mAdc, I_{B1} ≈ 10 mAdc, I_{B2} ≈ 10 mAdc)		2N4208 2N4209	t_s	— —	— —	15 20	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

Collector-Emitter Voltage	V_{CEO}	40	60	80	Vdc
Collector-Base Voltage	V_{CBO}	40	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	7.0			Vdc
Base Current	I_B	0.2			Vdc
Collector Current — Continuous	I_C	1.0 3.0*			Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.0 5.7			Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	6.0 34			Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200			°C

2N4235
2N4236

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

4

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	29	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage(1) (I_C = 100 mAdc, I_B = 0)	2N4234 2N4235 2N4236	$V_{CEO(sus)}$	40 60 80	— — —	Vdc
Collector Cutoff Current (V_{CE} = 30 Vdc, I_B = 0) (V_{CE} = 40 Vdc, I_B = 0) (V_{CE} = 60 Vdc, I_B = 0)	2N4234 2N4235 2N4236	I_{CEO}	— — —	1.0 1.0 1.0	mAdc
Collector Cutoff Current (V_{CE} = 40 Vdc, V_{BE} = 1.5 Vdc) (V_{CE} = 60 Vdc, V_{BE} = 1.5 Vdc) (V_{CE} = 80 Vdc, V_{BE} = 1.5 Vdc) (V_{CE} = 30 Vdc, V_{BE} = 1.5 Vdc, T_C = 150°C) (V_{CE} = 40 Vdc, V_{BE} = 1.5 Vdc, T_C = 150°C) (V_{CE} = 60 Vdc, V_{BE} = 1.5 Vdc, T_C = 150°C)	2N4234 2N4235 2N4236 2N4234 2N4235 2N4236	I_{CEX}	— — — — — —	0.1 0.1 0.1 1.0 1.0 1.0	mAdc
Collector Cutoff Current (V_{CB} = 40 Vdc, I_E = 0) (V_{CB} = 60 Vdc, I_E = 0) (V_{CB} = 80 Vdc, I_E = 0)	2N4234 2N4235 2N4236	I_{CBO}	— — —	0.1 0.1 0.1	mAdc
Emitter Cutoff Current (V_{BE} = 7 Vdc, I_C = 0)		I_{EBO}	—	0.5	mAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 100 mAdc, V_{CE} = 1.0 Vdc) (I_C = 250 mAdc, V_{CE} = 1.0 Vdc) (I_C = 500 mAdc, V_{CE} = 1.0 Vdc) (I_C = 1.0 Adc, V_{CE} = 1.0 Vdc)		h_{FE}	40 30 20 10	— 150 — —	—
Collector-Emitter Saturation Voltage(1) (I_C = 1.0 Adc, I_B = 125 mAdc)		$V_{CE(sat)}$	—	0.6	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 1.0 Adc, I_B = 100 mAdc)		$V_{BE(sat)}$	—	1.5	Vdc
Base-Emitter On Voltage (I_C = 250 mAdc, V_{CE} = 1.0 Vdc)		V_{BE}	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 100 mAdc, V_{CE} = 10 Vdc, f = 1.0 MHz)		f_T	3.0	—	MHz

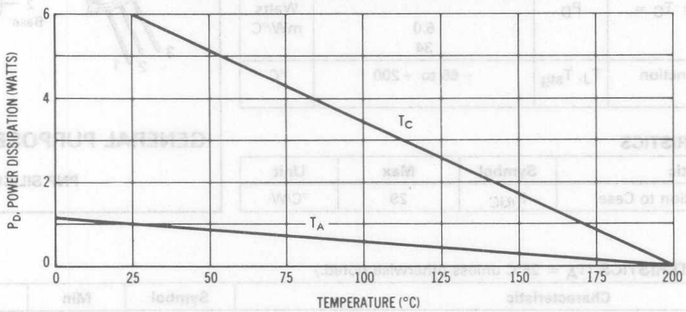
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	100	pF
Small-Signal Current Gain (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{fe}	25	—	—

(1) Pulse Test: PW ≤ 300 μs, Duty Cycle ≤ 2.0%.
*Indicates Data in addition to JEDEC Requirements.

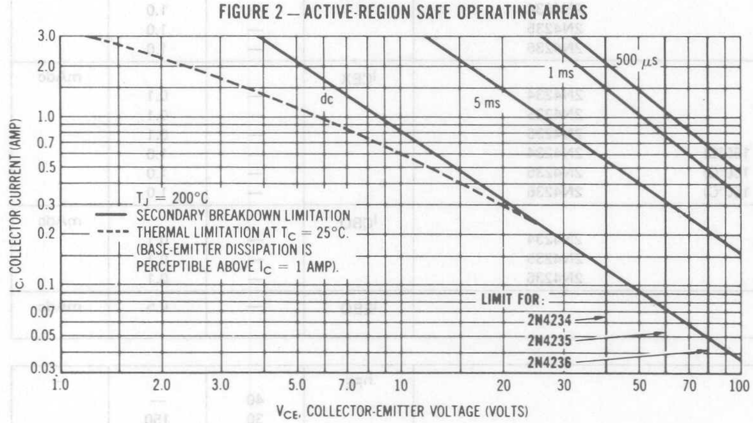
4

FIGURE 1 — POWER-TEMPERATURE DERATING CURVE



Safe Area Curves are indicated by Figure 2.
All limits are applicable and must be observed.

FIGURE 2 — ACTIVE-REGION SAFE OPERATING AREAS



The Safe Operating Area Curves indicate I_C — V_{CE} limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below the maximum T_J, power-temperature derating must be observed for both steady state and pulse power conditions.

LARGE SIGNAL CHARACTERISTICS

FIGURE 3 — TRANSCONDUCTANCE

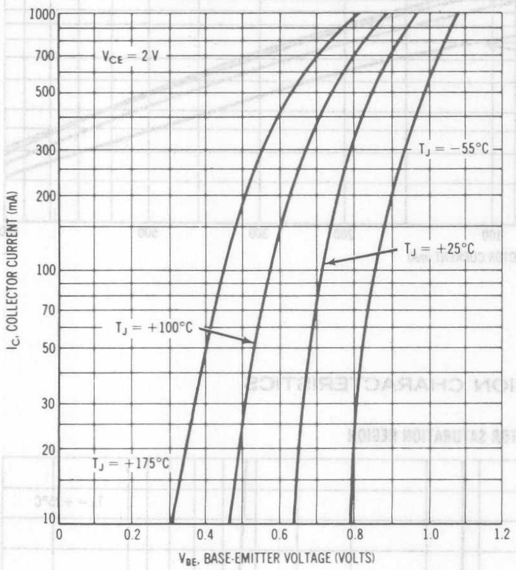
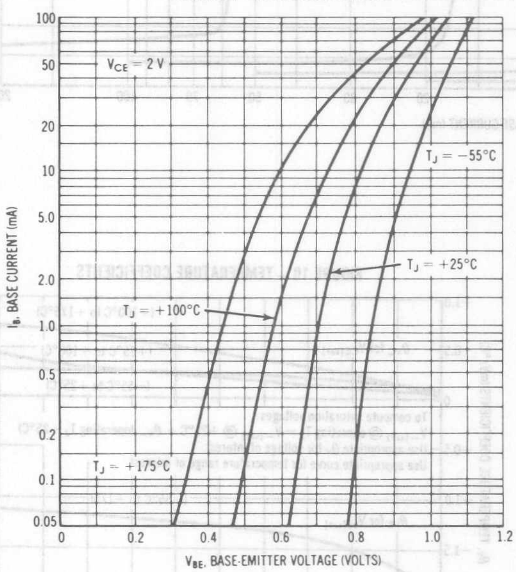


FIGURE 4 — INPUT ADMITTANCE



"OFF" REGION CHARACTERISTICS

FIGURE 5 — TRANSCONDUCTANCE

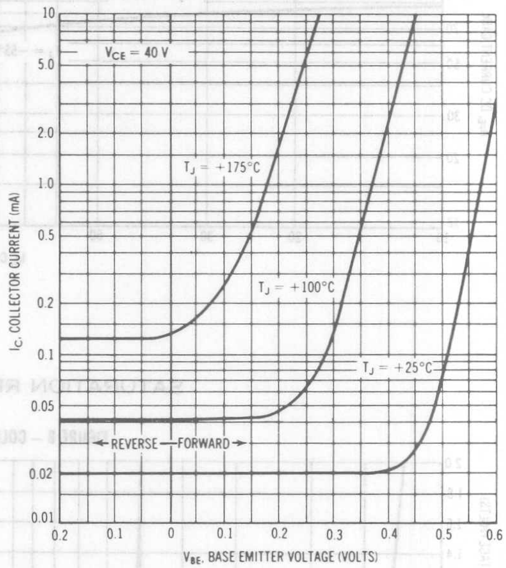
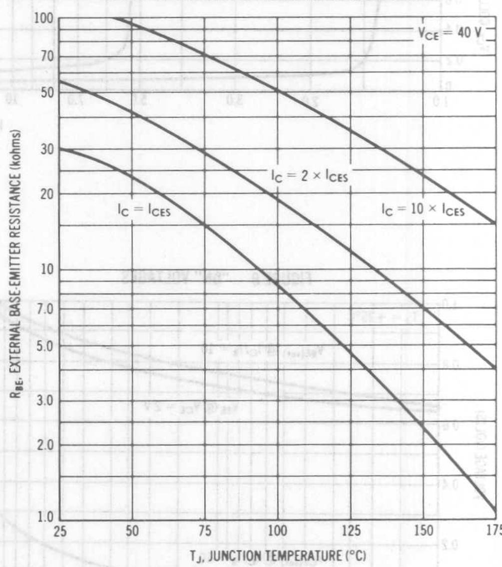
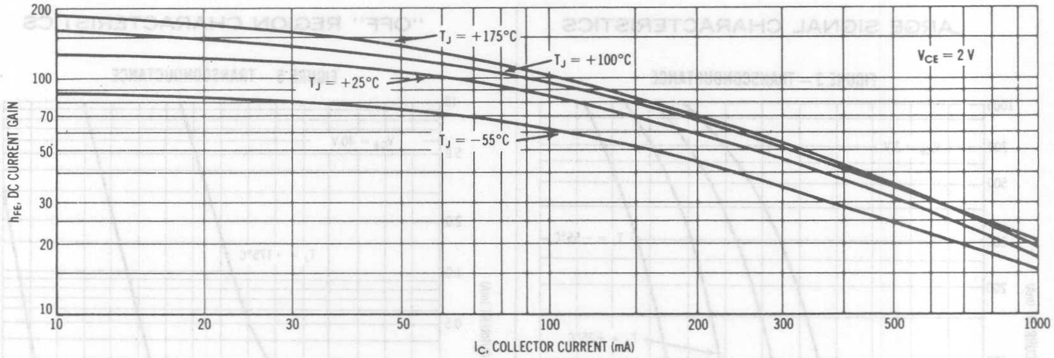


FIGURE 6 — EFFECTS OF BASE-EMITTER RESISTANCE



4

FIGURE 7 — CURRENT GAIN



SATURATION REGION CHARACTERISTICS

FIGURE 8 — COLLECTOR SATURATION REGION

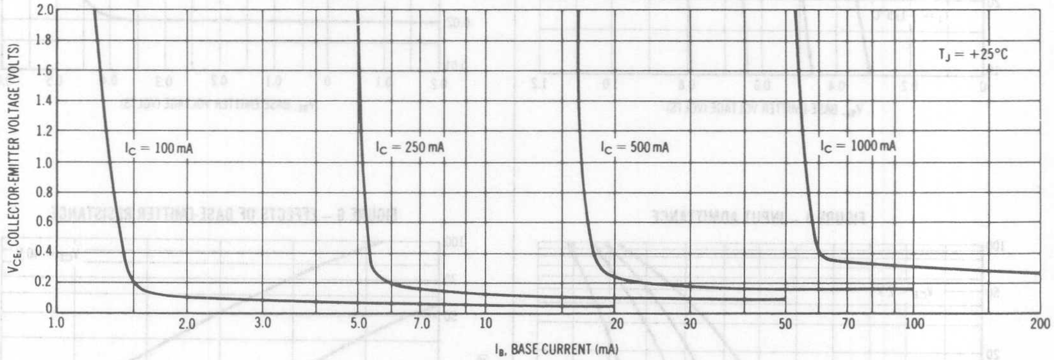


FIGURE 9 — "ON" VOLTAGES

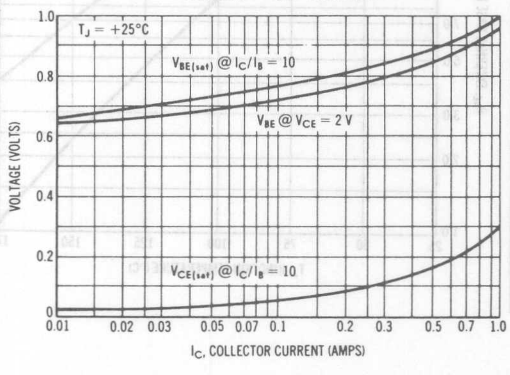


FIGURE 10 — TEMPERATURE COEFFICIENTS

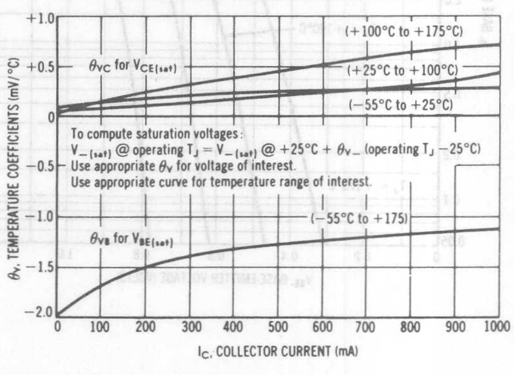


FIGURE 11 — TURN-ON TIME

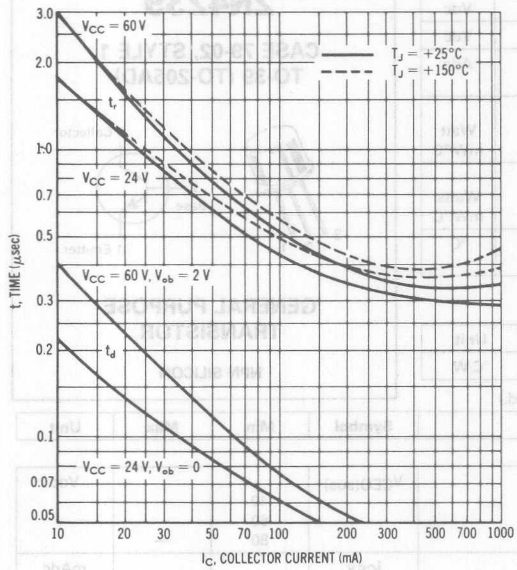


FIGURE 13 — CAPACITANCE

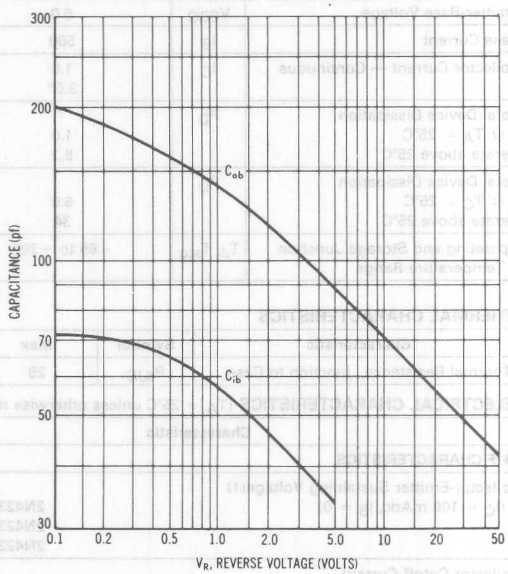


FIGURE 12 — STORAGE TIME

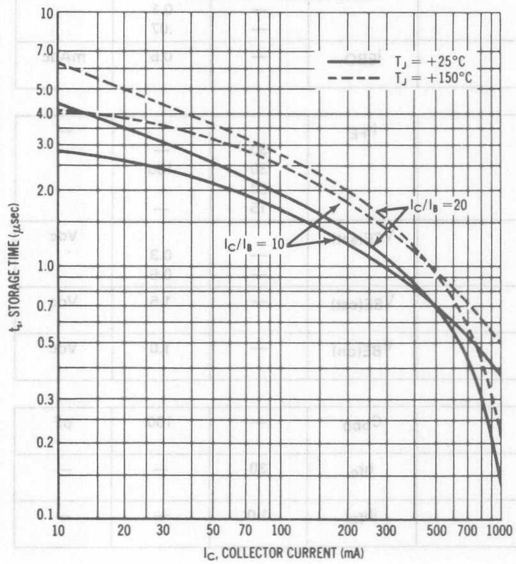
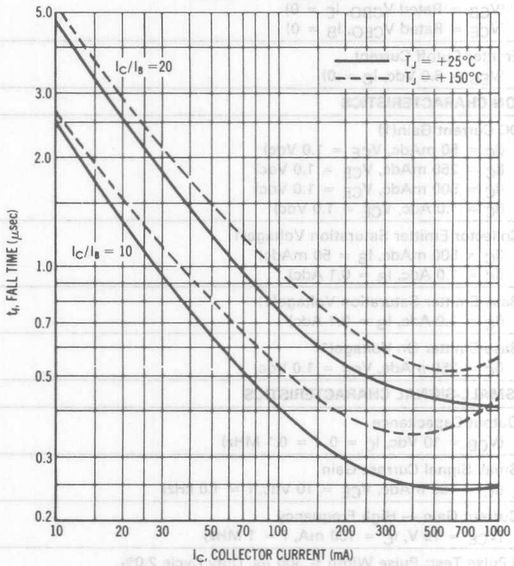


FIGURE 14 — FALL TIME

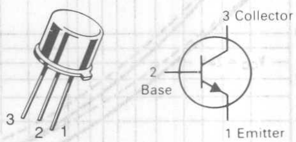


MAXIMUM RATINGS

Rating	Symbol	2N4237	2N4238	2N4239	Unit
Collector-Emitter Voltage	V_{CEO}	40	60	80	Vdc
Collector-Base Voltage	V_{CBO}	50	80	100	Vdc
Emitter-Base Voltage	V_{EBO}		6.0		Vdc
Base Current	I_B		500		Vdc
Collector Current — Continuous	I_C		1.0 3.0*		Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D		 1.0 5.3		 Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D		 6.0 34		 Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−65 to +200		°C

2N4237
2N4238
2N4239

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

THERMAL CHARACTERISTICS

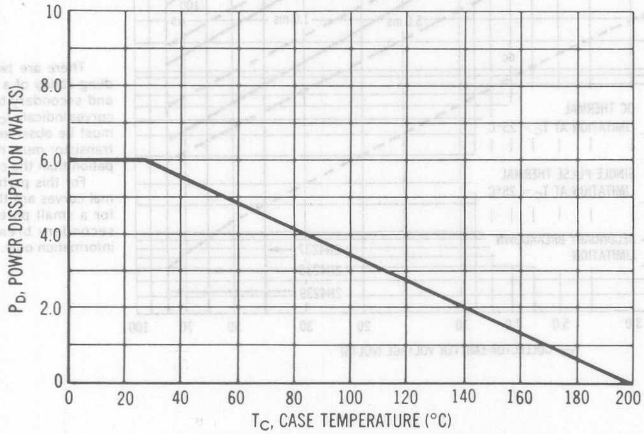
Characteristic	Symbol	Max	Unit
*Thermal Resistance, Junction to Case	$R_{\theta JC}$	29	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage(1) (I_C = 100 mAdc, I_B = 0)	 2N4237 2N4238 2N4239	$V_{CEO(sus)}$	 40 60 80	 — — —	Vdc
Collector Cutoff Current (V_{CE} = 50 Vdc, V_{EB} = 1.5 Vdc) (V_{CE} = 80 Vdc, V_{EB} = 1.5 Vdc) (V_{CE} = 100 Vdc, V_{EB} = 1.5 Vdc) (V_{CE} = 30 Vdc, V_{EB} = 1.5 Vdc, T_C = 150°C) (V_{CE} = 50 Vdc, V_{EB} = 1.5 Vdc, T_C = 150°C) (V_{CE} = 70 Vdc, V_{EB} = 1.5 Vdc, T_C = 150°C)	 2N4237 2N4238 2N4239 2N4237 2N4238 2N4239	I_{CEX}	 — — — — — —	 0.1 0.1 0.1 1.0 1.0 1.0	mAdc
Collector Cutoff Current (V_{CB} = Rated V_{CBO}, I_E = 0) (V_{CE} = Rated V_{CEO}, I_B = 0)		I_{CBO}	 — —	 0.1 .07	mAdc
Emitter Cutoff Current (V_{EB} = 6.0 Vdc, I_C = 0)		I_{EBO}	—	0.5	mAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 50 mAdc, V_{CE} = 1.0 Vdc) (I_C = 250 mAdc, V_{CE} = 1.0 Vdc) (I_C = 500 mAdc, V_{CE} = 1.0 Vdc) (I_C = 1.0 Adc, V_{CE} = 1.0 Vdc)		h_{FE}	 30 30 30 15	 — 150 — —	—
Collector-Emitter Saturation Voltage(1) (I_C = 500 mAdc, I_B = 50 mAdc) (I_C = 1.0 Adc, I_B = 0.1 Adc)		$V_{CE(sat)}$	 — —	 0.3 0.6	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 1.0 Adc, I_B = 0.1 Adc)		$V_{BE(sat)}$	—	1.5	Vdc
Base-Emitter On Voltage(1) (I_C = 250 mAdc, V_{CE} = 1.0 Vdc)		$V_{BE(on)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance (V_{CB} = 10 Vdc, I_C = 0, f = 0.1 MHz)		C_{obo}	—	100	pF
Small Signal Current Gain (I_C = 100 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{fe}	30	—	—
Current Gain — High Frequency (V_{CE} = 10 V, I_C = 100 mA, f = 1 MHz)		$\|h_{fe}\|$	1.0	—	—

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle 2.0%.
*Indicates Data in addition to JEDEC Requirements.

FIGURE 1 — POWER-TEMPERATURE DERATING CURVE



Safe Area Curves are indicated by Figure 5. All limits are applicable and must be observed.

SWITCHING CHARACTERISTICS

FIGURE 2 — SWITCHING TIME EQUIVALENT CIRCUIT

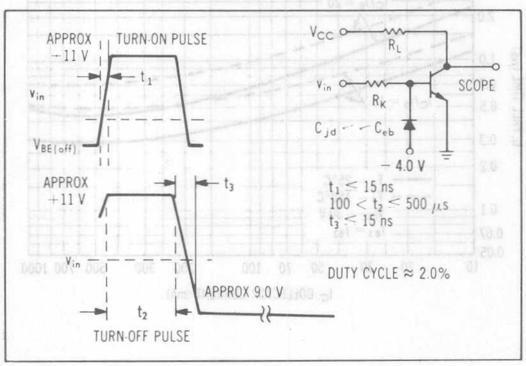


FIGURE 3 — TURN-ON TIME

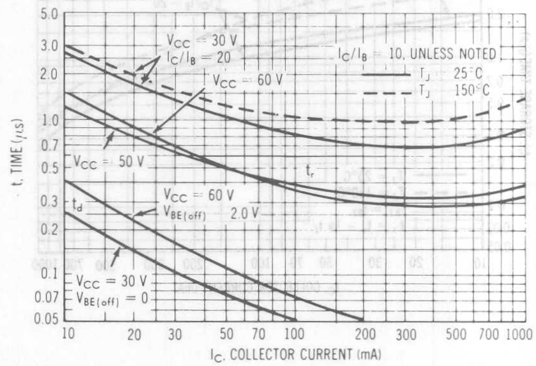


FIGURE 4 — THERMAL RESPONSE

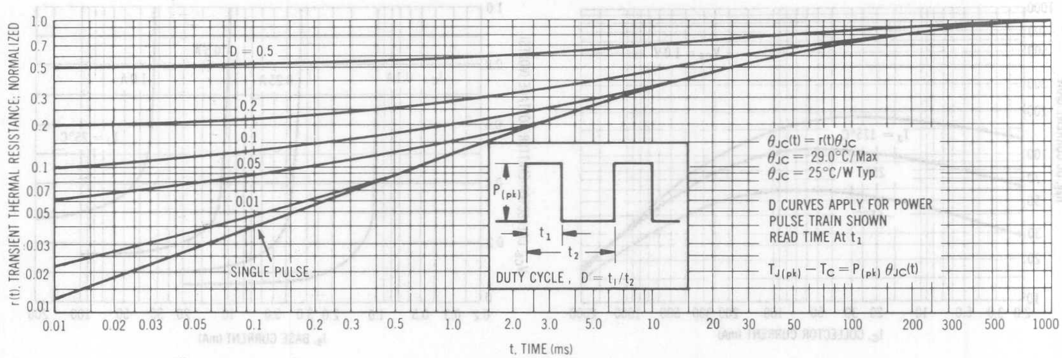
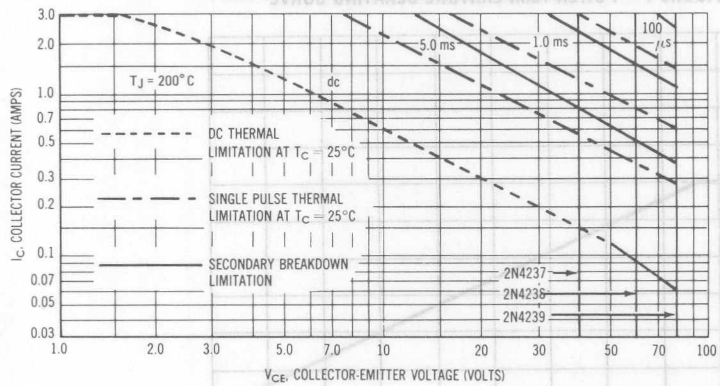


FIGURE 5 — ACTIVE-REGION SAFE OPERATING AREAS



There are two limitations on the power handling ability of a transistor: junction temperature and secondary breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

For this particular transistor family, the thermal curves are the limiting design values, except for a small portion of the dc curve. The pulse secondary breakdown curves are shown for information only.

4

FIGURE 6 — STORAGE TIME

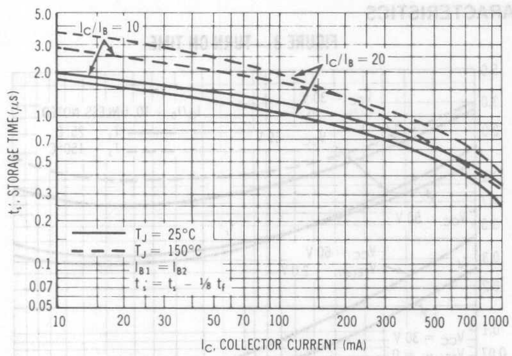
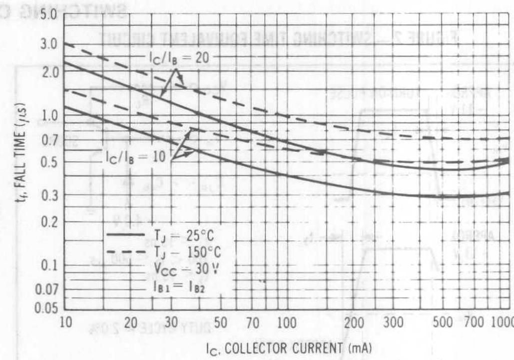


FIGURE 7 — FALL TIME



TYPICAL DC CHARACTERISTICS

FIGURE 8 — CURRENT GAIN

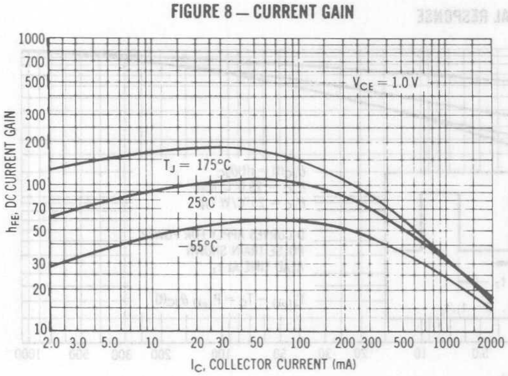


FIGURE 9 — COLLECTOR SATURATION REGION

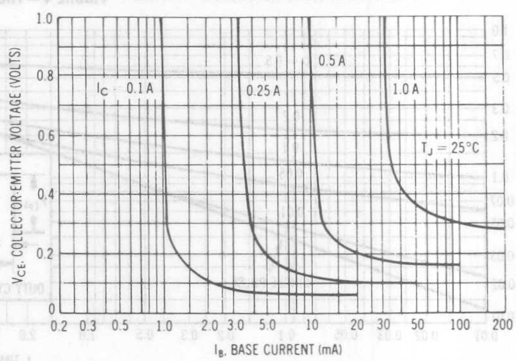


FIGURE 10 — EFFECTS OF BASE-EMITTER RESISTANCE

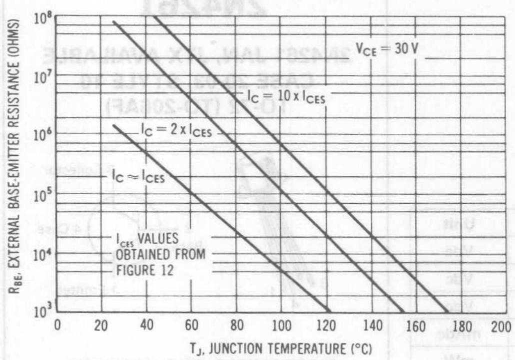


FIGURE 11 — "ON" VOLTAGE

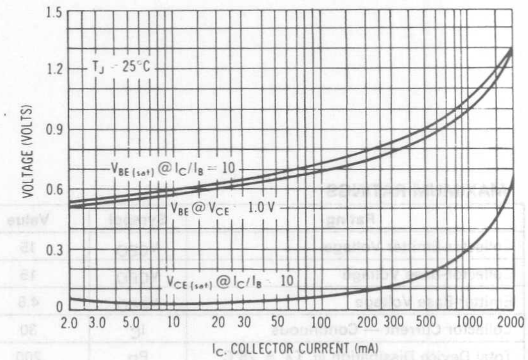


FIGURE 12 — COLLECTOR CUTOFF REGION

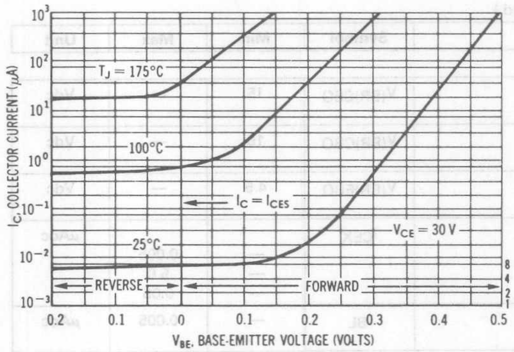
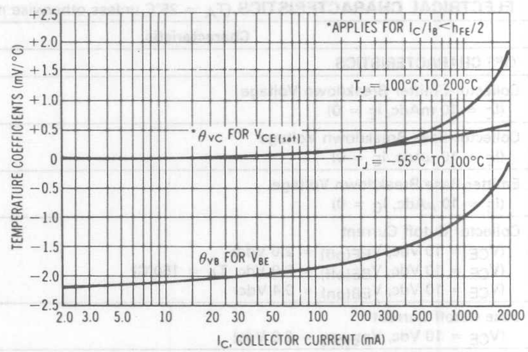


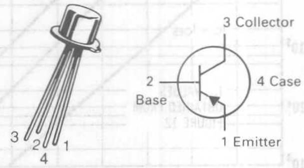
FIGURE 13 — TEMPERATURE COEFFICIENTS



4

2N4260
2N4261

2N4261 JAN, JTX AVAILABLE
CASE 20-03, STYLE 10
TO-72 (TO-206AF)



SWITCHING TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Base Voltage	V_{CBO}	15	Vdc
Emitter-Base Voltage	V_{EBO}	4.5	Vdc
Collector Current — Continuous	I_C	30	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	200 1.14	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_E = 0)		$V_{(BR)CEO}$	15	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	15	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	4.5	—	Vdc
Collector Cutoff Current (V_{CE} = 10 Vdc, $V_{BE(off)}$ = 2.0 Vdc) (V_{CE} = 10 Vdc, $V_{BE(off)}$ = 2.0 Vdc, T_A = 150°C) (V_{CE} = 10 Vdc, $V_{EB(on)}$ = 0.4 Vdc)		I_{CEX}	 — — —	 0.005 5.0 0.05	μAdc
Base Cutoff Current (V_{CE} = 10 Vdc, $V_{BE(off)}$ = 2.0 Vdc)		I_{BL}	—	0.005	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc) (I_C = 30 mAdc, V_{CE} = 2.0 Vdc)		h_{FE}	 25 30 20	 — 150 —	—
Collector-Emitter Saturation Voltage (I_C = 1.0 mAdc, I_B = 0.1 mAdc) (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{CE(sat)}$	 — —	 0.15 0.35	Vdc
Base-Emitter On Voltage (I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc)		$V_{BE(on)}$	 — —	 0.8 1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 5.0 mAdc, V_{CE} = 4.0 Vdc, f = 100 MHz) (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	 2N4260 2N4261 2N4260 2N4261	f_T	 1200 1500 1600 2000	 — — — —	MHz
Output Capacitance (V_{CB} = 4.0 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	2.5	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	2.5	pF
Current Gain — High Frequency (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	2N4260 2N4261	$\|h_{fe}\|$	16 20	— —	—

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Collector Base Time Constant		$r_b'C_c$			ps
(I_C = 5.0 mAdc, V_{CE} = 4.0 Vdc, f = 31.8 MHz)	2N4260		—	35	
	2N4261		—	60	
(I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 31.8 MHz)	2N4260		—	30	
	2N4261		—	50	

SWITCHING CHARACTERISTICS

Characteristic	Symbol	Typical Performance (v_{out} = 1.0 V) @ 10 mA	Typical Performance (v_{out} = 1.0 V) @ 30 mA	Unit
Rise Time	t_r	0.5	0.9	ns
Fall Time	t_f	1.0	1.2	ns
Turn-On Time	$t_{on(delay)}$	1.0	1.2	ns
Turn-Off Delay Time	$t_{off(delay)}$	1.0	1.2	ns

FIGURE 1 — DC CURRENT GAIN

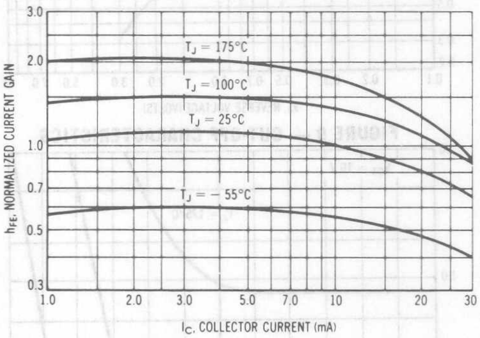


FIGURE 2 — COLLECTOR SATURATION REGION

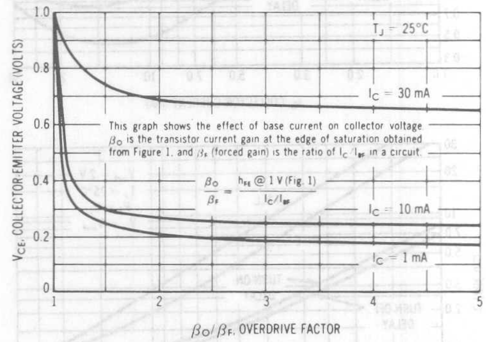


FIGURE 3 — "ON" VOLTAGES

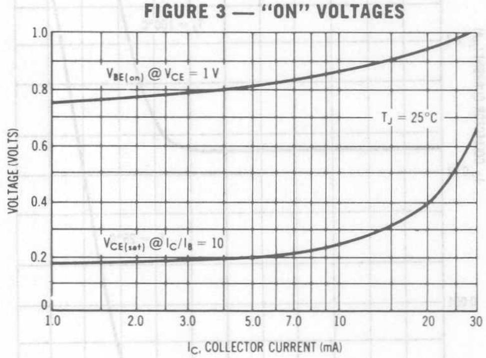


FIGURE 4 — TEMPERATURE COEFFICIENTS

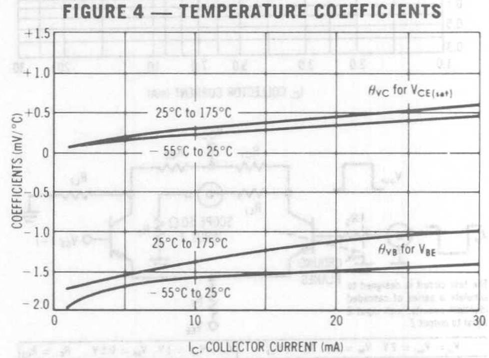


FIGURE 5 — CURRENT-GAIN — BANDWIDTH PRODUCT

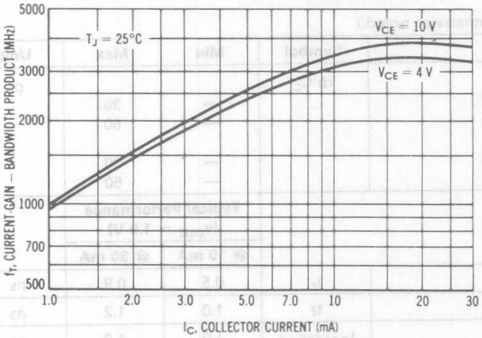


FIGURE 6 — COLLECTOR-BASE TIME CONSTANT

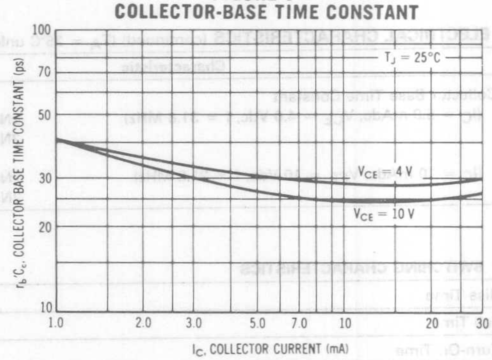
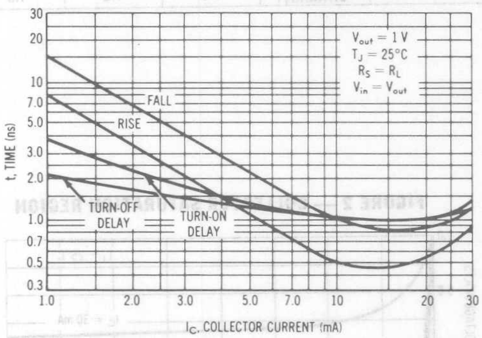
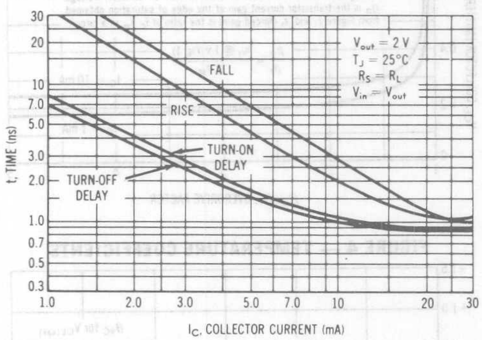
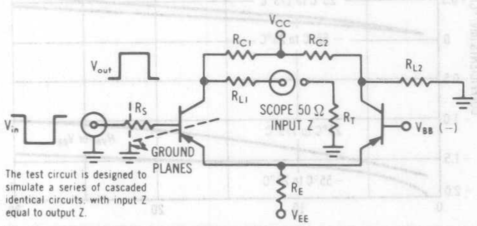


FIGURE 7 — SWITCHING TIMES







The test circuit is designed to simulate a series of cascaded identical circuits, with input Z equal to output Z.

$V_{in} = V_{out} = 2$ V $V_{BB} = 1$ V $R_{C1} = R_{C2}$								$V_{in} = V_{out} = 1$ V $V_{BB} = 0.5$ V $R_{C1} = R_{C2}$						
I_C mA	R_S ohms	R_C ohms	R_{L1} ohms	R_{L2} ohms	R_E ohms	V_{EE} volts	V_{CC} volts	R_S ohms	R_C ohms	R_{L1} ohms	R_{L2} ohms	R_E ohms	V_{EE} volts	V_{CC} volts
1	2 k	6 k	3 k	3 k	10 k	10	16	1 k	6 k	1.2 k	1.2 k	24 k	24	32
5	360	3.56 k	400	450	2 k	10	47	175	1 k	200	250	3 k	15	27
10	160	1 k	200	250	3 k	30	26.3	75	300	100	150	3 k	30	17
20	62	300	100	150	1 k	20	16	25	150	25	75	1 k	20	11
30	28	157	66	116	1 k	30	13	8	77	0	50	1 k	30	9

FIGURE 8 — CAPACITANCE

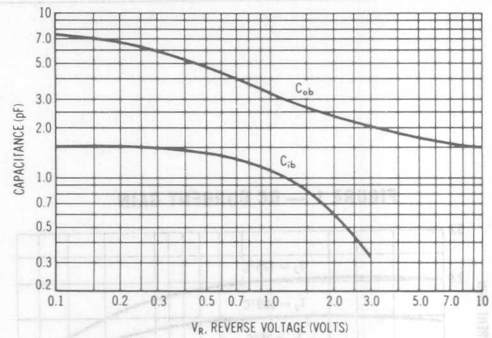
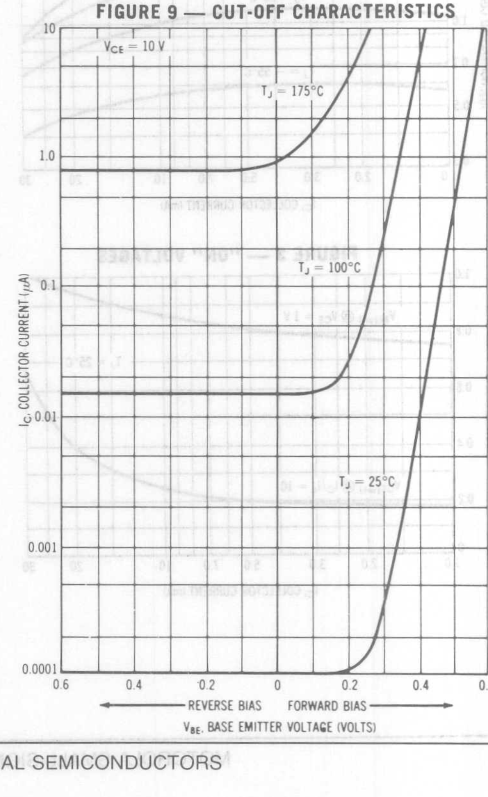
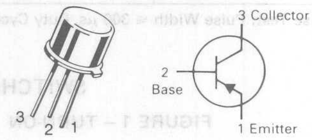


FIGURE 9 — CUT-OFF CHARACTERISTICS



2N4405

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

4

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	80	Vdc
Collector-Base Voltage	V_{CBO}	80	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	1.0	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.25 7.15	Watts mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	8.75 50	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	25	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	140	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	80	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)		$V_{(BR)CBO}$	80	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 60$ Vdc, $I_E = 0$)		I_{CBO}	—	25	nAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)		I_{EBO}	—	25	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 5.0$ Vdc)	 2N4404 2N4405	h_{FE}	 30 75	 — —	—
($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc)	2N4404 2N4405		40 100	— —	
($I_C = 150$ mAdc, $V_{CE} = 5.0$ Vdc)(1)	2N4404 2N4405		40 100	120 300	
($I_C = 500$ mAdc, $V_{CE} = 5.0$ Vdc)(1)	2N4404 2N4405		30 50	— —	
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 150$ mAdc, $I_B = 15$ mAdc)(1) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)(1)		$V_{CE(sat)}$	 — — —	 0.15 0.2 0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)(1)		$V_{BE(sat)}$	 — 0.85	 0.8 1.2	Vdc
Base-Emitter On Voltage ($I_C = 150$ mAdc, $V_{CE} = 1.0$ Vdc)		$V_{BE(on)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)		f_T	200	600	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{cb}	—	10	pF
Emitter-Base Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)		C_{eb}	—	75	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 30 Vdc, $V_{BE(off)}$ = 2.0 Vdc, I_C = 500 mAdc, I_{B1} = 50 mAdc)	t_d	—	15	ns
Rise Time		t_r	—	25	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 500 mAdc, I_{B1} = I_{B2} = 50 mAdc)	t_s	—	175	ns
Fall Time		t_f	—	35	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

4

SWITCHING TIME EQUIVALENT TEST CIRCUITS

FIGURE 1 — TURN-ON

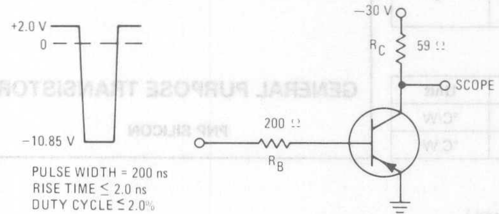
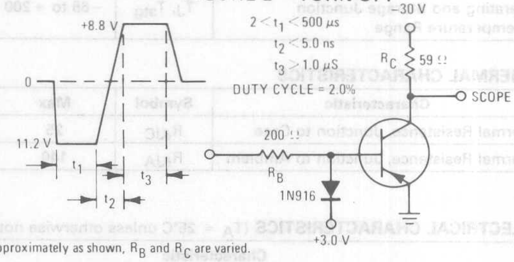


FIGURE 2 — TURN-OFF



To obtain data for curves, voltage levels are approximately as shown, R_B and R_C are varied.

TRANSIENT CHARACTERISTICS

——— 25°C   — — — 100°C

FIGURE 3 — CAPACITANCES

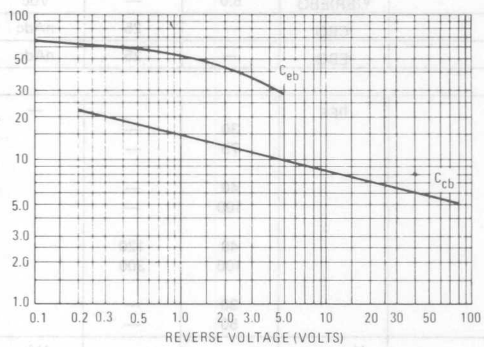


FIGURE 4 — CHARGE DATA

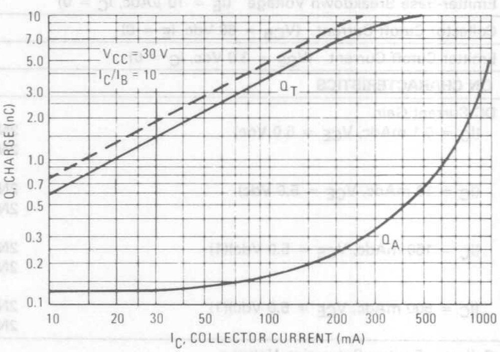


FIGURE 5 — DELAY TIME

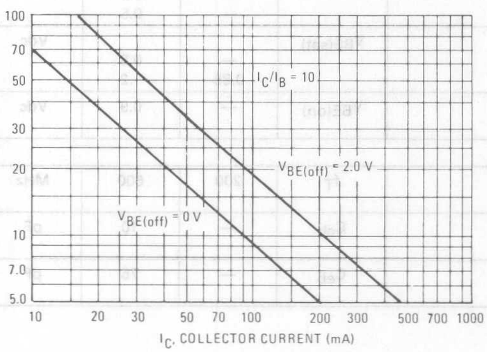
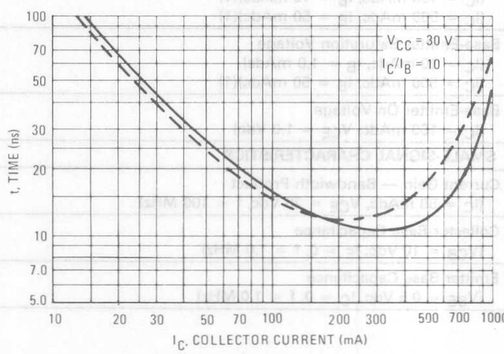


FIGURE 6 — RISE TIME



4

FIGURE 7 – STORAGE TIME

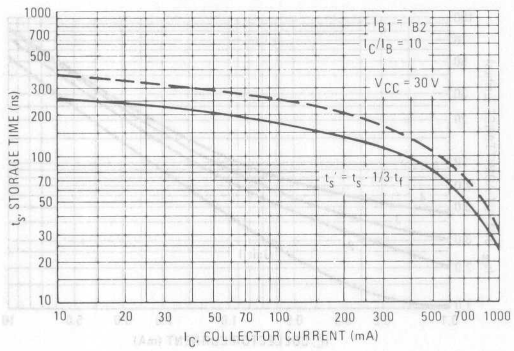
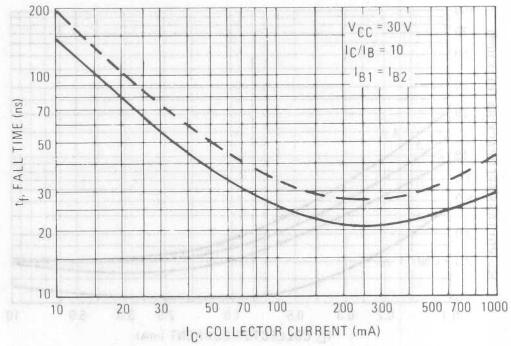


FIGURE 8 – FALL TIME



SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE

$V_{CE} = 10$ Vdc, $T_A = 25°C$

FIGURE 9 – FREQUENCY EFFECTS

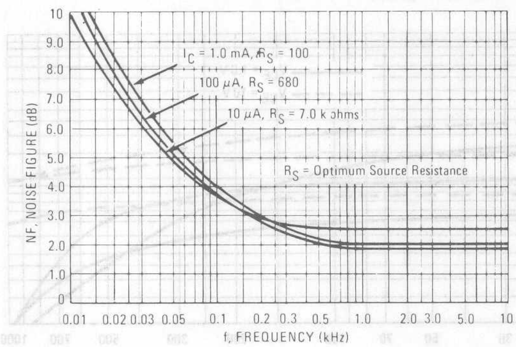
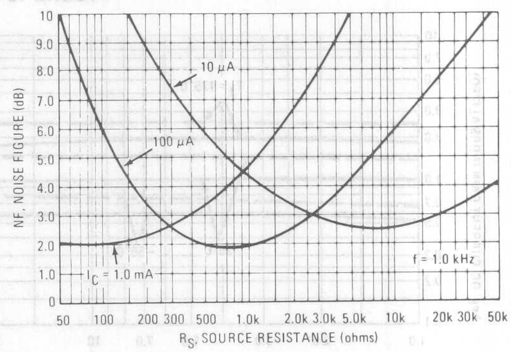


FIGURE 10 – SOURCE RESISTANCE EFFECTS



h PARAMETERS

$V_{CE} = 10$ Vdc, f = 1.0 kHz, $T_A = 25°C$

This group of graphs illustrates the relationship of the "h" parameters for this series of transistors. To obtain these curves, 4 units were selected and identified by number – the same units were used to develop curves on each graph.

FIGURE 11 – CURRENT GAIN

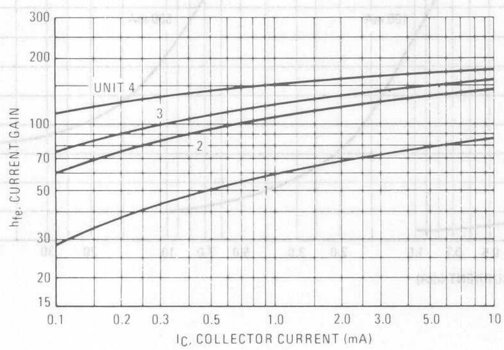
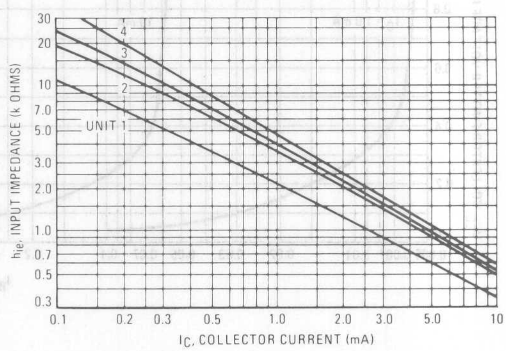
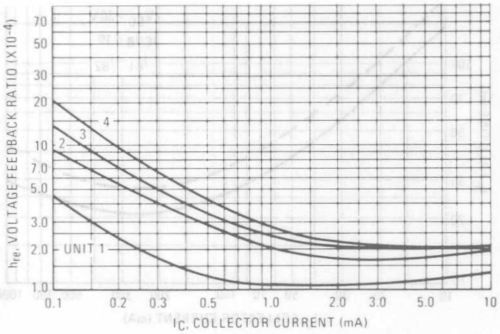
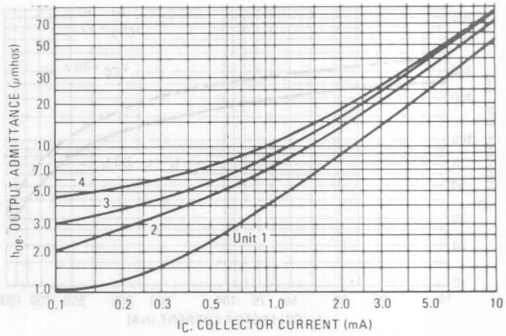


FIGURE 12 – INPUT IMPEDANCE







STATIC CHARACTERISTICS

FIGURE 15 – DC CURRENT GAIN

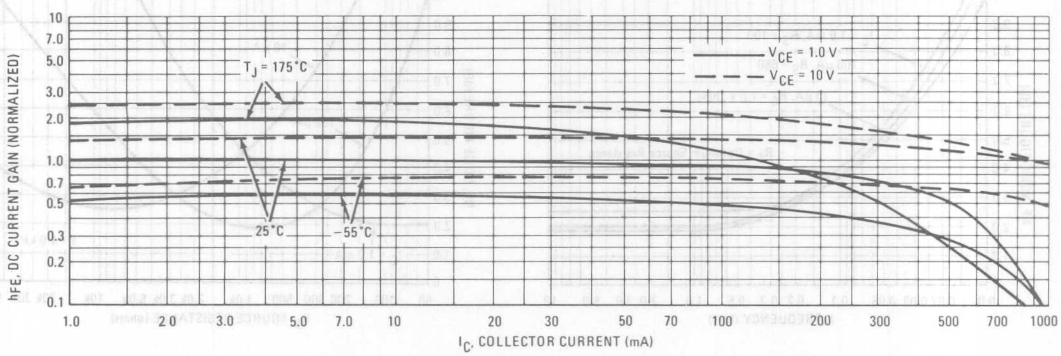
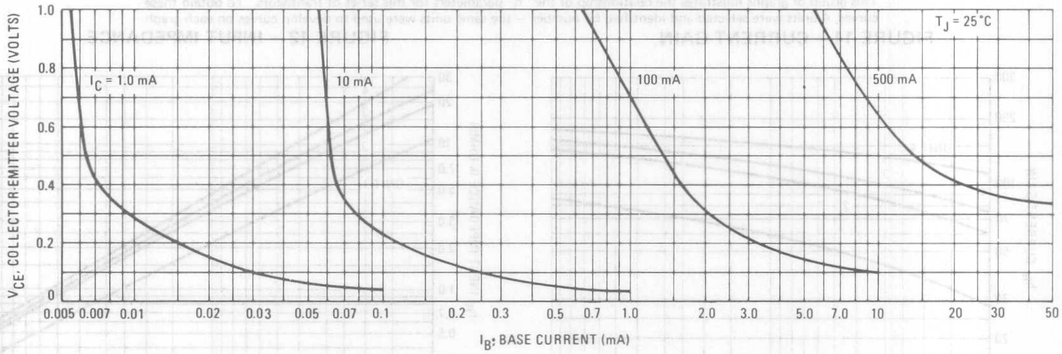
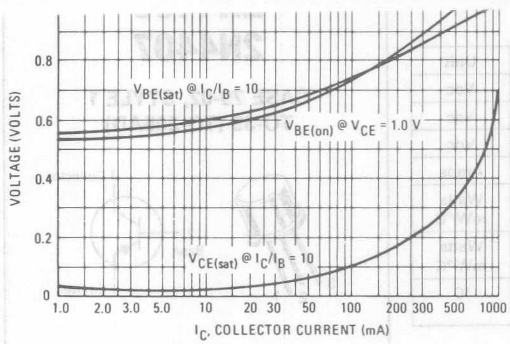
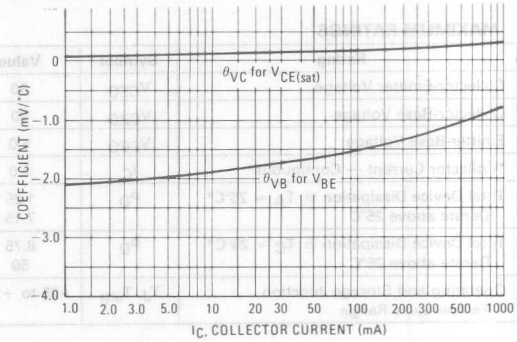


FIGURE 16 – COLLECTOR SATURATION REGION

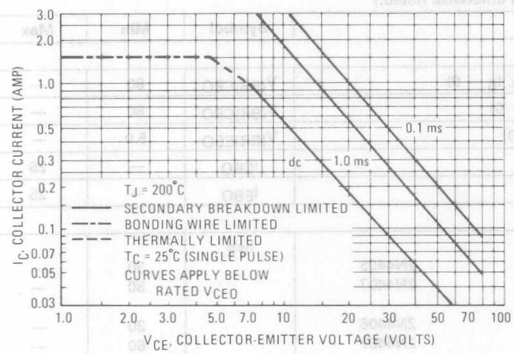






RATINGS AND THERMAL DATA

FIGURE 19 – SAFE OPERATING AREA



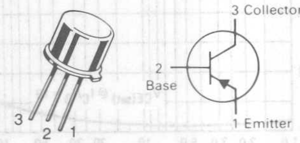
The safe operating area curves indicate I_C V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 19 is based upon $T_{J(pk)}$ = 200°C; T_C is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 200°C$. $T_{J(pk)}$ may be calculated from the data in Figure 20. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

4

2N4406
2N4407

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	80	Vdc
Collector-Base Voltage	V_{CBO}	80	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	2.0	Amps
Total Device Dissipation @ $T_A = 25°C$* Derate above 25°C	P_D	1.25 7.15	Watts mW/°C
Total Device Dissipation @ $T_C = 25°C$* Derate above 25°C	P_D	8.75 50	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	20	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	140	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	80	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)		$V_{(BR)CBO}$	80	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 60$ Vdc, $I_E = 0$)		I_{CBO}	—	25	nAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)		I_{EBO}	—	25	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc)	2N4406 2N4407	h_{FE}	30 80	— —	—
($I_C = 150$ mAdc, $V_{CE} = 5.0$ Vdc)	2N4406 2N4407		30 80	— —	
($I_C = 500$ mAdc, $V_{CE} = 5.0$ Vdc)	2N4406 2N4407		30 80	120 240	
($I_C = 1.0$ Adc, $V_{CE} = 5.0$ Vdc)	2N4406 2N4407		20 30	— —	
($I_C = 1.5$ Adc, $V_{CE} = 5.0$ Vdc)	2N4406, 2N4407		10	—	
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc) ($I_C = 1.0$ Adc, $I_B = 100$ mAdc) ($I_C = 1.5$ Adc, $I_B = 150$ mAdc)		$V_{CE(sat)}$	 — — — —	 0.2 0.4 0.7 1.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 1.0$ Adc, $I_B = 100$ mAdc) ($I_C = 1.5$ Adc, $I_B = 150$ mAdc)		$V_{BE(sat)}$	 — 0.9 —	 0.9 1.3 1.5	Vdc
Base-Emitter On Voltage ($I_C = 500$ mAdc, $V_{CE} = 1.0$ Vdc)		$V_{BE(on)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)		f_T	150	750	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{cb}	—	15	pF
Emitter-Base Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)		C_{eb}	—	160	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 30 Vdc, $V_{BE(off)}$ = 2.0 Vdc, I_C = 1.0 Adc, I_{B1} = 100 mAdc)	t_d	—	15	ns
Rise Time		t_r	—	60	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 1.0 Adc, I_{B1} = I_{B2} = 100 mAdc)	t_s	—	175	ns
Fall Time		t_f	—	50	ns

(1) Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.
*Indicates Data in addition to JEDEC Requirements.

4

FIGURE 1 — DC CURRENT GAIN

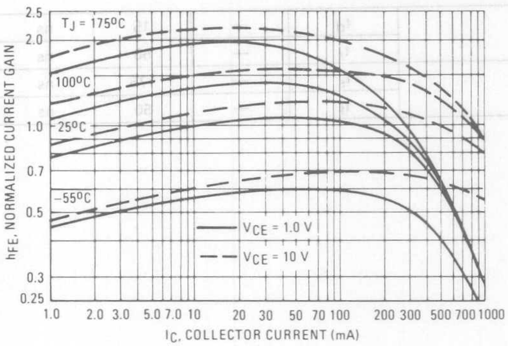


FIGURE 2 — COLLECTOR SATURATION REGION

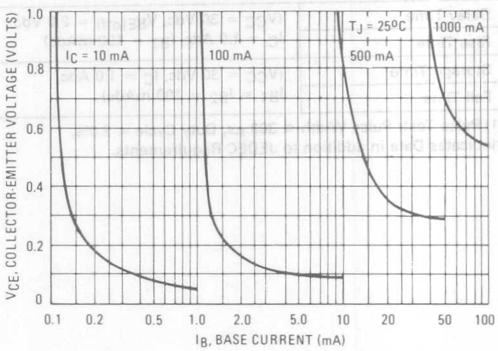


FIGURE 3 — "ON" VOLTAGES

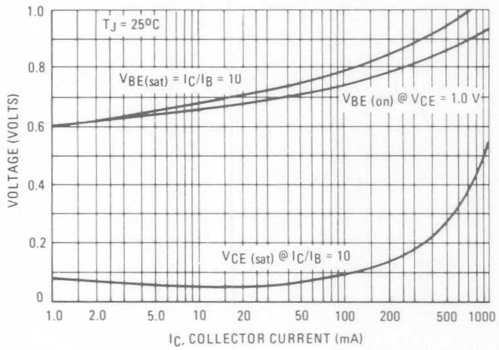


FIGURE 4 — TEMPERATURE COEFFICIENTS

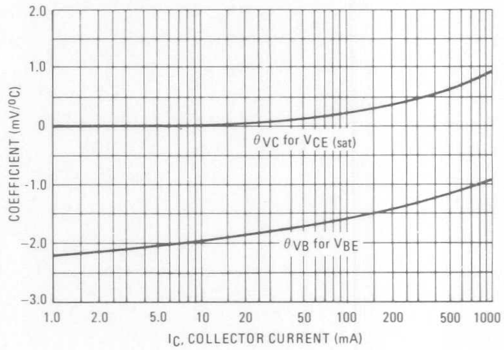
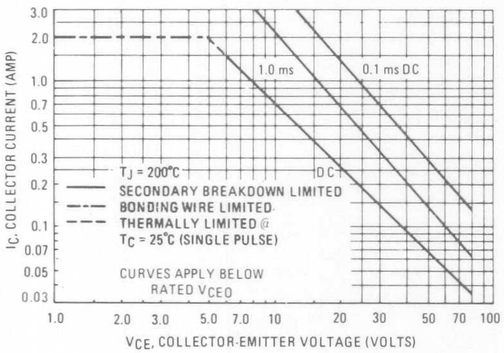


FIGURE 5 — SAFE OPERATING AREA



The safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 5 is based upon $T_{J(pk)}$ = 200°C; T_C is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 200°C$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

TRANSIENT CHARACTERISTICS

——— 25°C – – – 100°C

FIGURE 7 - CAPACITANCES

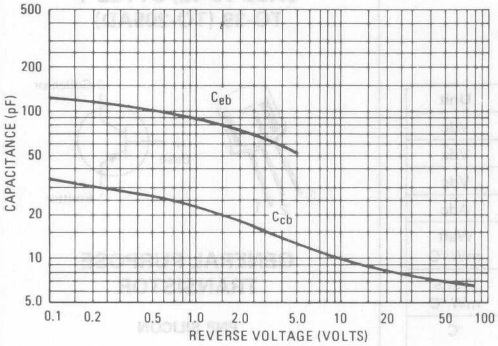


FIGURE 8 - CHARGE DATA

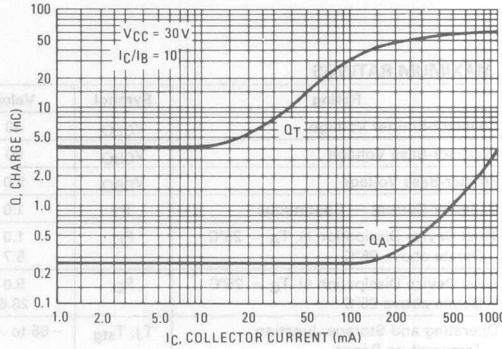


FIGURE 9 - TURN-ON TIME

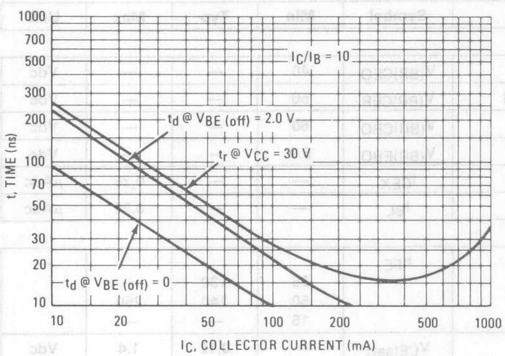
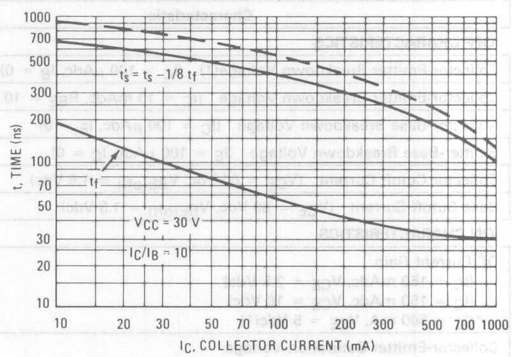


FIGURE 10 - TURN-OFF TIME



SWITCHING TIME EQUIVALENT TEST CIRCUITS

FIGURE 11 - TURN-ON TIME

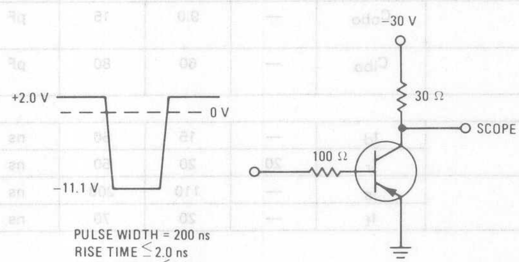
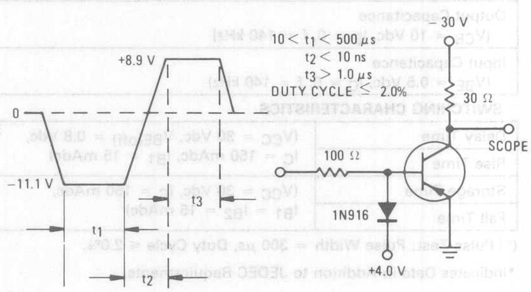


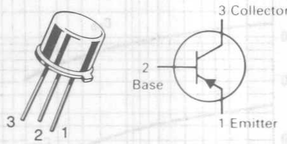
FIGURE 12 - TURN-OFF TIME



2N4453 For Specifications, See 2N869A Data.

2N4890

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

Refer to 2N4033 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	1.0	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 5.7	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5.0 28.6	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

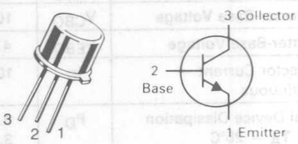
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 100\ \mu Adc$, $I_B = 0$)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 10$ mAdc, $R_{BE} = 10$ ohms)	$V_{(BR)CER}$	50	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu Adc$, $I_E = 0$)	$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu Adc$, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CE} = 60$ Vdc, $V_{BE(off)} = 1.5$ Vdc)	I_{CEX}	—	—	0.25	μAdc
Base Cutoff Current ($V_{CE} = 60$ Vdc, $V_{BE(off)} = 1.5$ Vdc)	I_{BL}	—	—	0.25	μAdc
ON CHARACTERISTICS					
DC Current Gain	h_{FE}				—
($I_C = 150$ mAdc, $V_{CE} = 2.5$ Vdc)		25	130	—	
($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)		50	140	250	
*($I_C = 500$ mA, $V_{CE} = 5$ Vdc(1))		15	—	—	
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{CE(sat)}$	—	0.12	1.4	Vdc
Base-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{BE(sat)}$	—	0.82	1.7	Vdc
Base-Emitter On Voltage ($I_C = 150$ mAdc, $V_{CE} = 2.5$ Vdc)	$V_{BE(on)}$	—	0.74	1.7	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)	f_T	100	280	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 140 kHz)	C_{obo}	—	9.0	15	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 140 kHz)	C_{ibo}	—	60	80	pF
SWITCHING CHARACTERISTICS					
Delay Time ($V_{CC} = 30$ Vdc, $V_{BE(off)} = 0.8$ Vdc, $I_C = 150$ mAdc, $I_{B1} = 15$ mAdc)	t_d	—	15	50	ns
Rise Time ($V_{CC} = 30$ Vdc, $V_{BE(off)} = 0.8$ Vdc, $I_C = 150$ mAdc, $I_{B1} = 15$ mAdc)	t_r	20	20	50	ns
Storage Time ($V_{CC} = 30$ Vdc, $I_C = 150$ mAdc, $I_{B1} = I_{B2} = 15$ mAdc)	t_s	—	110	200	ns
Fall Time ($V_{CC} = 30$ Vdc, $I_C = 150$ mAdc, $I_{B1} = I_{B2} = 15$ mAdc)	t_f	—	20	70	ns

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

*Indicates Data in Addition to JEDEC Requirements.

2N4926
2N4927

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



AMPLIFIER TRANSISTOR

NPN SILICON

4

MAXIMUM RATINGS

Rating	Symbol	2N4926	2N4927	Unit
Collector-Emitter Voltage	V_{CEO}	200	250	Vdc
Collector-Base Voltage	V_{CBO}	200	250	Vdc
Emitter-Base Voltage	V_{EBO}	7.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 5.71		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5.0 28.6		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	175	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

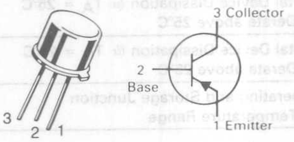
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (1) ($I_C = 10$ mAdc, $I_B = 0$)	2N4926 2N4927	$V_{(BR)CEO}$	200 250	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.1$ mAdc, $I_C = 0$)	2N4926 2N4927	$V_{(BR)CBO}$	200 250	— 	Vdc
Emitter-Base Breakdown Voltage ($I_E = 0.1$ mAdc, $I_C = 0$)		$V_{(BR)EBO}$	7.0		Vdc
Collector Cutoff Current ($V_{CB} = 100$ Vdc, $I_E = 0$) ($V_{CB} = 100$ Vdc, $I_E = 0$, $T_A = 100°C$) ($V_{CB} = 150$ Vdc, $I_E = 0$) ($V_{CB} = 150$ Vdc, $I_E = 0$, $T_A = 100°C$)	2N4926 2N4927	I_{CBO}	— — — —	0.1 10 0.1 10	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc)		I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS (1)					
DC Current Gain	($I_C = 3.0$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 30$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 50$ mAdc, $V_{CE} = 20$ Vdc)	h_{FE}	10 15 20 20	— — 200 	
Collector-Emitter Saturation Voltage	($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 30$ mAdc, $I_B = 3.0$ mAdc)	$V_{CE(sat)}$	— —	1.0 2.0	Vdc
Base-Emitter Saturation Voltage	($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 3.0$ mAdc)	$V_{BE(sat)}$	— —	1.2 1.5	Vdc
Base-Emitter On Voltage ($I_C = 30$ mAdc, $V_{CE} = 10$ Vdc)		$V_{BE(on)}$	—	1.5	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 20 MHz)		f_T	30	300	MHz
Collector-Base Capacitance ($V_{CB} = 20$ Vdc, $I_E = 0$, f = 140 kHz)		C_{cb}	—	6.0	pF
Input Impedance ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)		h_{ie}	75	2000	ohm
Voltage Feedback Ratio ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)		h_{re}	0.1	2.0	X 10^{-4}
Small-Signal Current Gain ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)		h_{fe}	25	250	—
Output Admittance ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)		h_{oe}	—	50	μmhos
Real Part of Input Impedance ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 5.0 MHz)		$Re(h_{ie})$	4.0	200	ohms

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2N4931

2N4930 and 2N4931 JAN, JTX & JTXV AVAILABLE

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	2N4928	2N4929	2N4930	2N4931	Unit
Collector-Emitter Voltage	V_{CEO}	100	150	200	250	Vdc
Collector-Base Voltage	V_{CBO}	100	150	200	250	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	4.0	4.0	4.0	Vdc
Collector Current — Continuous	I_C	100	500	500	500	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.6 3.4	1.0 5.71	1.0 5.71	1.0 5.71	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	3.0 17.2	5.0 28.6	5.0 28.6	5.0 28.6	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		–65 to +200			°C

Refer to 2N3494 for graphs for 2N4928.*

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	2N4928 2N4929 2N4930 2N4931	$V_{(BR)CEO}$	100 150 200 250	— — — —	Vdc
Collector-Base Breakdown Voltage (I_E = 0, I_C = 100 μAdc)	2N4928 2N4929 2N4930 2N4931	$V_{(BR)CBO}$	100 150 200 250	— — — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0) (V_{CB} = 75 Vdc, I_E = 0) (V_{CB} = 150 Vdc, I_E = 0)	2N4928 2N4929 2N4930, 2N4931	I_{CBO}	— — —	0.5 0.5 1.0	μAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0) (V_{BE} = 3.0 Vdc, I_C = 0)	2N4928, 2N4929 2N4930, 2N4931	I_{EBO}	— —	0.5 1.0	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc)	All Types	h_{FE}	20	—	—
(I_C = 10 mAdc, V_{CE} = 10 Vdc)(1)	2N4928, 2N4929 2N4930, 2N4931		25 20	200 200	
(I_C = 50 mAdc, V_{CE} = 10 Vdc)(1) (I_C = 30 mAdc, V_{CE} = 10 Vdc)(1)	2N4928, 2N4929 2N4930, 2N4931		20 20	— —	
Collector-Emitter Saturation Voltage(1) (I_C = 10 mAdc, I_B = 1.0 mAdc)	2N4928, 2N4929 2N4930, 2N4931	$V_{CE(sat)}$	— —	0.5 5.0	Vdc
Base-Emitter On Voltage (I_C = 10 mAdc, V_{CE} = 10 Vdc)		$V_{BE(on)}$	—	1.0	Vdc

Characteristic		Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product		f_T			MHz
(I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	2N4928, 2N4929		100	1,000	
(I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 20 MHz)	2N4930, 2N4931		20	200	
Collector-Base Capacitance		C_{cb}			pF
(V_{CB} = 20 Vdc, I_E = 0, f = 140 kHz)	2N4928		—	6.0	
(V_{CB} = 20 Vdc, I_E = 0, f = 140 kHz)	2N4929		—	10	
(V_{CB} = 20 Vdc, I_E = 0, f = 140 kHz)	2N4930, 2N4931		—	20	
Emitter-Base Capacitance		C_{eb}			pF
(V_{BE} = 2.0 Vdc, I_C = 0, f = 140 kHz)	2N4928		—	40	
(V_{BE} = 1.0 Vdc, I_C = 0, f = 140 kHz)	2N4929		—	80	
(V_{BE} = 0.5 Vdc, I_C = 0, f = 140 kHz)	2N4930, 2N4931		—	400	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
Refer to 2N3634 for graphs for 2N4929.
Refer to 2N3743 for graphs for 2N4930 and 2N4931.

MAXIMUM RATINGS

Rating	Symbol	2N5022	2N5023	Unit
Collector-Emitter Voltage	V_{CEO}	50	30	V
Collector-Emitter Voltage	V_{CES}	50	30	V
Collector-Base Voltage	V_{CBO}	50	30	V
Emitter-Base Voltage	V_{EBO}	5		V
Collector Current — Continuous (Pulse Width = 300 μs, DC = 1%)	I_C	1.0*		A
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.0 5.72		Watts mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	4.0 22.8		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C
Maximum Lead Temperature (Soldering, 60 sec max)	T_L	+300		°C

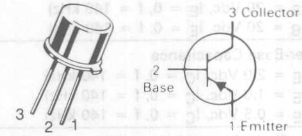
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	43.8	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	175	°C/W

*Indicates Data in Addition to JEDEC Requirements.

2N5022
2N5023

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

Refer to 2N3467 for graphs.

4

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 100 μAdc)	2N5022	$V_{(BR)CES}$	50	—	V
	2N5023		30	—	
Collector-Emitter Sustaining Voltage (I_C = 10 mAdc)	2N5022	$V_{(BR)CEO(sus)}$*	50	—	V
	2N5023		30	—	
Collector-Base Breakdown Voltage (I_C = 100 μAdc)	2N5022	$V_{(BR)CBO}$	50	—	V
	2N5023		30	—	
Emitter-Base Breakdown Voltage (I_E = 100 μAdc)	All	$V_{(BR)EBO}$	5.0	—	V
Collector Cutoff Current (V_{CE} = 30 Vdc)	2N5022	I_{CES}	—	100	nA
(V_{CE} = 20 Vdc) (T_A = 100°Cdc)	2N5023		—	15	μA
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 100 mA, V_{CE} = 1.0 Vdc)	2N5022	h_{FE}	15	—	—
	2N5023		30	—	
(I_C = 500 mA, V_{CE} = 1.0 Vdc)	2N5022		25	100	
	2N5023		40	100	
(I_C = 1.0 A, V_{CE} = 5.0 Vdc)	2N5022		25	—	
	2N5023		40	—	
(I_C = 500 ma, V_{CE} = 1.0 V, T_A = −55°C)	2N5022		10	—	
	2N5023		20	—	
Collector-Emitter Saturation Voltage(1) (I_C = 100 mAdc, I_B = 10 mAdc)	2N5022	$V_{CE(sat)}$	—	0.20	
	2N5023		—	0.17	V
(I_C = 500 mAdc, I_B = 50 mAdc)	2N5022		—	0.40	
	2N5023		—	0.35	V
(I_C = 1.0 Adc, I_B = 100 mAdc)	2N5022		—	0.80	
	2N5023		—	0.70	V

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

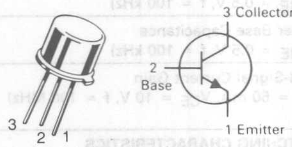
Characteristic		Symbol	Min	Max	Unit
Base-Emitter Saturation Voltage		$V_{BE(sat)}$			
(I_C = 100 mAdc, I_B = 10 mAdc)			—	1.0	V
(I_C = 500 mAdc, I_B = 50 mAdc)			0.8	1.4	V
(I_C = 1.0 Adc, I_B = 100 mAdc)			—	1.75	V
SMALL-SIGNAL CHARACTERISTICS					
Collector-Base Capacitance (V_{BE} = 0.5 V, f = 100 kHz)		C_{cb}	—	25	pF
Emitter-Base Capacitance (V_{BE} = 0.5 V, f = 100 kHz)		C_{eb}	—	100	pF
Small-Signal Current Gain (I_C = 50 mA, V_{CE} = 10 V, f = 100 MHz)		h_{fe}			
	2N5022		1.7	—	
	2N5023		2.0	—	
SWITCHING CHARACTERISTICS					
Turn-On Time (V_{CE} = −30 V, I_C ≈ 500 mA, I_B ≈ 50 mA)		t_{on}	—	40	ns
Turn-Off Time (V_{CE} = 30 V, I_C ≈ 500 mA, I_{B1} = I_{B2} ≈ 50 mA)		t_{off}	—	90	ns

(1) Pulse Width = 300 μs, Duty Cycle = 1.0%.

4

2N5058
2N5059

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N3724 for graphs.

MAXIMUM RATINGS

Rating	Symbol	2N5058	2N5059	Unit
Collector-Emitter Voltage	V_{CEO}	300	250	Vdc
Collector-Base Voltage	V_{CBO}	300	250	Vdc
Emitter-Base Voltage	V_{EBO}	7.0	6.0	Vdc
Collector Current — Continuous	I_C	150		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.0 6.67		Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	5.0 33.3		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

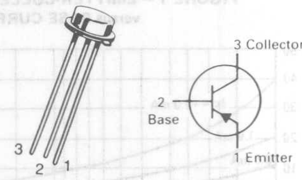
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	30	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$ (1)	150	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (2) (I_C = 30 mAdc, I_B = 0)	 2N5058 2N5059	$V_{(BR)CEO}$	 300 250	 — —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	 2N5058 2N5059	$V_{(BR)CBO}$	 300 250	 — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	 2N5058 2N5059	$V_{(BR)EBO}$	 7.0 6.0	 — —	Vdc
Collector Cutoff Current (V_{CB} = 100 Vdc, I_E = 0) (V_{CB} = 100 Vdc, I_E = 0, T_A = +125°C)		I_{CBO}	— —	0.05 20	μAdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)		I_{EBO}	—	10	nAdc
ON CHARACTERISTICS (2)					
DC Current Gain (I_C = 5.0 mAdc, V_{CE} = 25 Vdc)	 2N5058 2N5059	h_{FE}	 10 10	 — —	—
(I_C = 30 mAdc, V_{CE} = 25 Vdc)	2N5058 2N5059		35 30	150 150	
(I_C = 30 mAdc, V_{CE} = 25 Vdc, T_A = −55°C)	2N5058		10	—	
(I_C = 100 mAdc, V_{CE} = 25 Vdc)	2N5058 2N5059		35 30	— —	
Collector-Emitter Saturation Voltage (I_C = 30 mAdc, I_B = 3.0 mAdc)		$V_{CE(sat)}$	—	1.0	Vdc
Base-Emitter Saturation Voltage (I_C = 30 mAdc, I_B = 3.0 mAdc)		$V_{BE(sat)}$	—	0.85	Vdc
Base-Emitter On Voltage (I_C = 30 mAdc, V_{CE} = 25 Vdc)		$V_{BE(on)}$	—	0.82	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (3) (I_C = 10 mAdc, V_{CE} = 25 Vdc, f = 20 MHz)		f_T	30	160	MHz
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{cb}	—	10	pF
Emitter-Base Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{eb}	—	75	pF

(1) $R\theta_{JA}$ is measured with the device soldered into a typical printed circuit board.
(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(3) f_T is defined as the frequency at which the $|h_{fe}|$ extrapolates to unity.

CASE 26-03, STYLE 1
TO-46 (TO-206AB)



LOW POWER CHOPPER TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Emitter-Collector Voltage	V_{ECO}	20	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	30	Vdc
Collector Current — Continuous	I_C	50	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.5 2.86	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	2.0 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Emitter-Collector Breakdown Voltage (I_E = 10 μAdc, I_B = 0)	$V_{(BR)ECO}$	20	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	30	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	30	—	Vdc
Collector Cutoff Current (V_{CB} = 25 Vdc, I_E = 0)	I_{CBO}	—	1.0	nAdc
Emitter Cutoff Current (V_{EB} = 25 Vdc, I_C = 0)	I_{EBO}	—	1.0	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 100 μAdc, V_{CE} = 1.0 Vdc) (I_C = 200 μAdc, V_{CE} = 0.5 Vdc) (Inverted Connection)	h_{FE}	 50 15	 — —	—
Offset Voltage (I_B = 100 μAdc, I_E = 0) (I_B = 1.0 mAdc, I_E = 0)	$V_{EC(ofs)}$	 — —	 0.5 1.0	mVdc
SMALL-SIGNAL CHARACTERISTICS				
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 140 kHz)	C_{cb}	—	5.0	pF
Emitter-Base Capacitance (V_{EB} = 10 Vdc, I_C = 0, f = 140 kHz)	C_{eb}	—	4.0	pF
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 4.0 MHz)	h_{fe}	2.0	—	—
"ON" Series Resistance (I_B = 1.0 mAdc, I_E = 0, I_e = 100 μA RMS, f = 1.0 kHz)	$r_{ec(on)}$	2.0	8.0	Ohms

TYPICAL CHARACTERISTICS

FIGURE 1 – EMITTER-COLLECTOR VOLTAGE versus BASE CURRENT

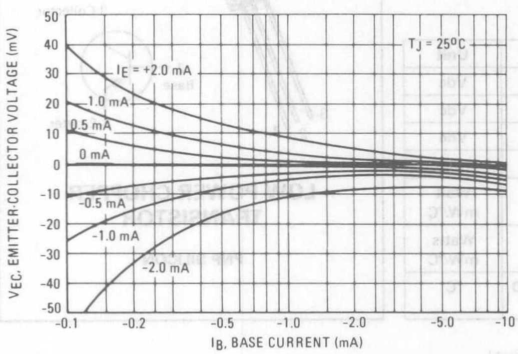


FIGURE 2 – EMITTER-COLLECTOR VOLTAGE versus JUNCTION TEMPERATURE

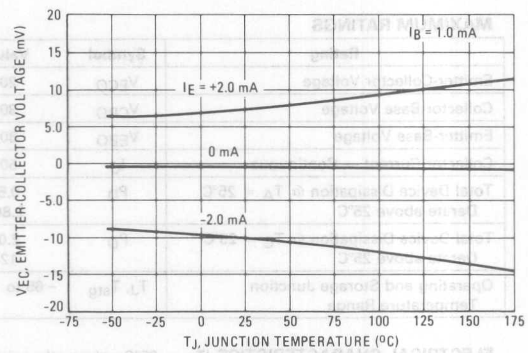


FIGURE 3 – EMITTER-COLLECTOR "ON" RESISTANCE versus BASE CURRENT

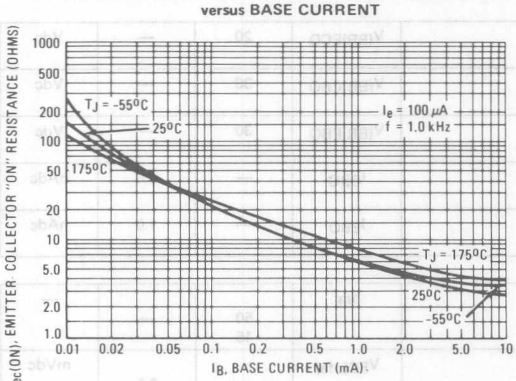


FIGURE 4 – EMITTER-COLLECTOR "ON" RESISTANCE TEMPERATURE COEFFICIENT versus BASE CURRENT

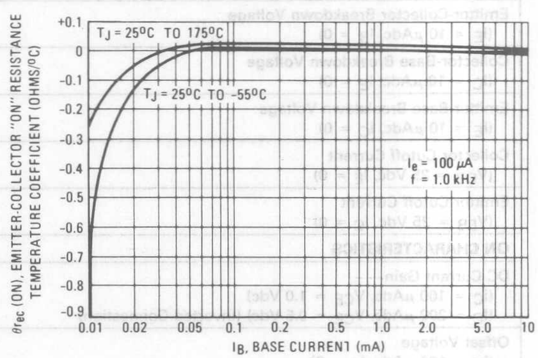


FIGURE 5 – CURRENT GAIN versus COLLECTOR CURRENT

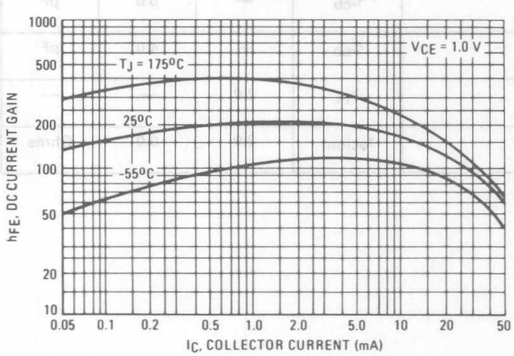


FIGURE 6 – CURRENT GAIN (Inverted Connection) versus EMITTER CURRENT

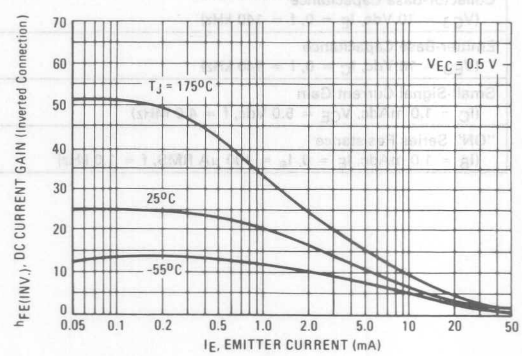


FIGURE 7 – COLLECTOR CUTOFF CURRENT versus JUNCTION TEMPERATURE

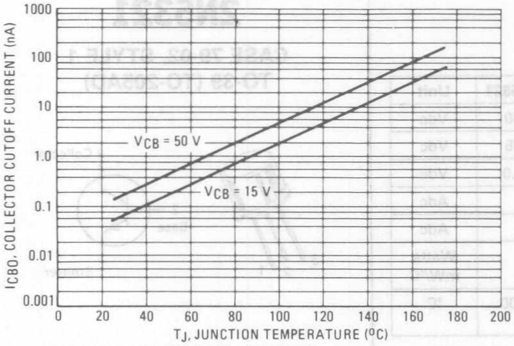


FIGURE 8 – EMITTER CUTOFF CURRENT versus JUNCTION TEMPERATURE

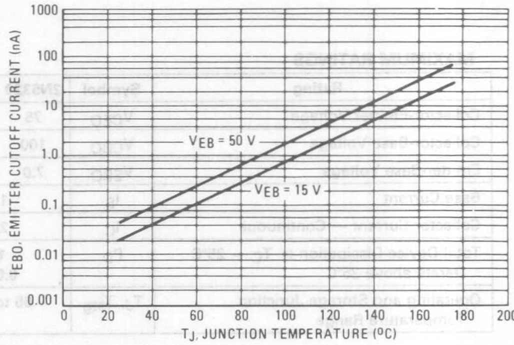


FIGURE 9 – COLLECTOR-EMITTER SATURATION VOLTAGE versus COLLECTOR CURRENT

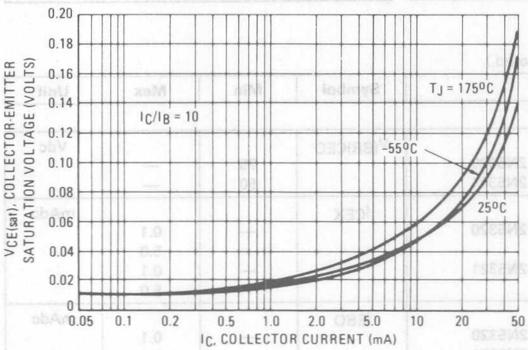
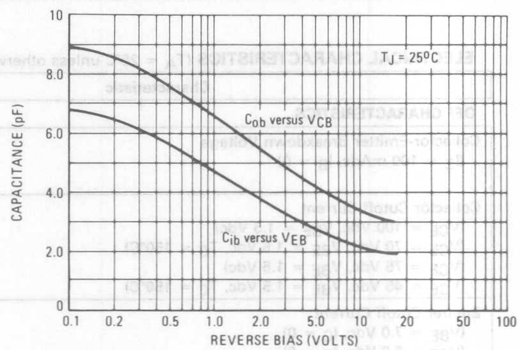


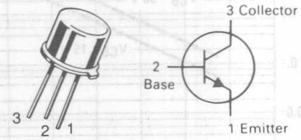
FIGURE 10 – JUNCTION CAPACITANCE versus REVERSE BIAS VOLTAGE



4

2N5320
2N5321

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



SWITCHING TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	2N5320	2N5321	Unit
Collector-Emitter Voltage	V_{CEO}	75	50	Vdc
Collector-Base Voltage	V_{CBO}	100	75	Vdc
Emitter-Base Voltage	V_{EBO}	7.0	5.0	Vdc
Base Current	I_B	1.0		Adc
Collector Current — Continuous	I_C	2.0		Adc
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	10 0.057		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

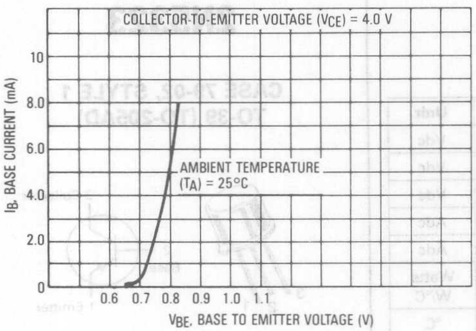
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	17.5	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

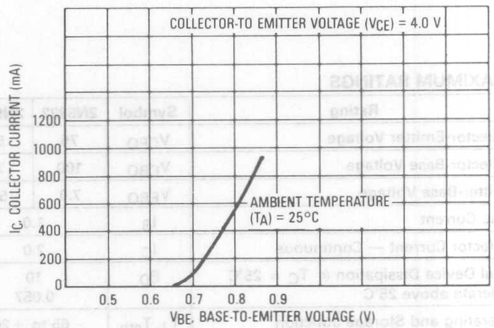
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 100 mAdc, I_B = 0)	 2N5320 2N5321	$V_{(BR)CEO}$	 75 50	 — —	Vdc
Collector Cutoff Current (V_{CE} = 100 Vdc, V_{BE} = 1.5 Vdc) (V_{CE} = 70 Vdc, V_{BE} = 1.5 Vdc, T_C = 150°C) (V_{CE} = 75 Vdc, V_{BE} = 1.5 Vdc) (V_{CE} = 45 Vdc, V_{BE} = 1.5 Vdc, T_C = 150°C)	 2N5320 2N5321 	I_{CEX}	 — — — —	 0.1 5.0 0.1 5.0	mAdc
Emitter Cutoff Current (V_{BE} = 7.0 Vdc, I_C = 0) (V_{BE} = 5.0 Vdc, I_C = 0)	 2N5320 2N5321	I_{EBO}		 0.1 0.1	mAdc
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 500 mAdc, V_{CE} = 4.0 Vdc) (I_C = 1.0 Adc, V_{CE} = 2.0 Vdc)	 2N5320 2N5321 2N5320	h_{FE}	 30 40 10	 130 250 —	—
Collector-Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc)	 2N5320 2N5321	$V_{CE(sat)}$	 — —	 0.5 0.8	Vdc
Base-Emitter On Voltage (I_C = 500 mAdc, V_{CE} = 4.0 Vdc)	 2N5320 2N5321	$V_{BE(on)}$	 —	 1.1 1.4	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Small-Signal Current Gain (I_C = 50 mAdc, V_{CE} = 4.0 Vdc, f = 10 MHz)		h_{fe}	5	—	—
SWITCHING CHARACTERISTICS					
Turn-On Time (V_{CC} = 30 Vdc, I_C = 500 mAdc, I_{B1} = 50 mAdc)		t_{on}	—	80	ns
Turn-Off Time (V_{CC} = 30 Vdc, I_C = 500 mAdc, $I_{B1} = I_{B2}$ = 50 mAdc)		t_{off}	—	800	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

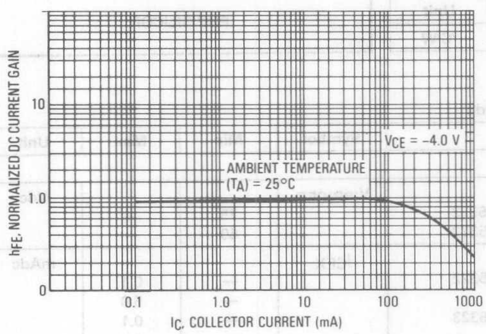
TYPICAL INPUT CHARACTERISTICS



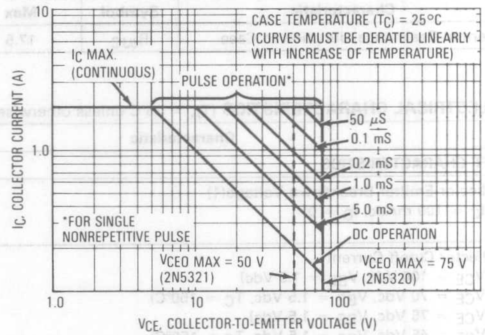
TYPICAL TRANSFER CHARACTERISTICS



CURRENT GAIN CHARACTERISTICS versus COLLECTOR-EMITTER VOLTAGE

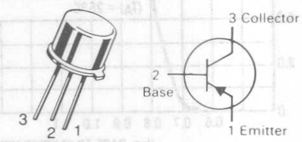


MAXIMUM SAFE OPERATING AREAS (SOA)



2N5322
2N5323

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



SWITCHING TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	2N5322	2N5323	Unit
Collector-Emitter Voltage	V_{CEO}	75	50	Vdc
Collector-Base Voltage	V_{CBO}	100	75	Vdc
Emitter-Base Voltage	V_{EBO}	7.0	5.0	Vdc
Base Current	I_B	1.0		Adc
Collector Current — Continuous	I_C	2.0		Adc
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	10 0.057		Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

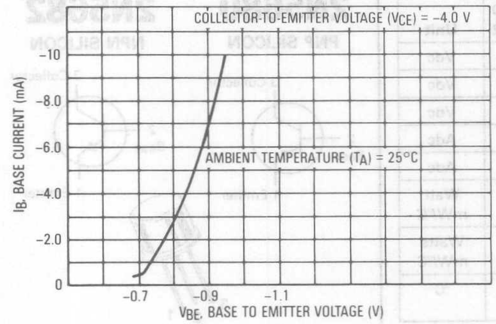
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	17.5	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

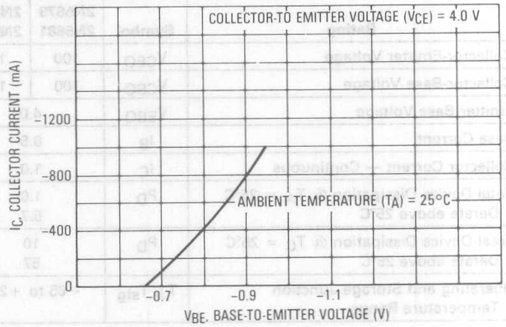
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1)		$V_{(BR)CEO}$			Vdc
($I_C = 100$ mAdc, $I_B = 0$)	2N5322		75	—	
	2N5323		50	—	
Collector Cutoff Current		I_{CEX}			mAdc
($V_{CE} = 100$ Vdc, $V_{BE} = 1.5$ Vdc)	2N5322		—	0.1	
($V_{CE} = 70$ Vdc, $V_{BE} = 1.5$ Vdc, $T_C = 150°C$)			—	5.0	
($V_{CE} = 75$ Vdc, $V_{BE} = 1.5$ Vdc)	2N5323		—	0.1	
($V_{CE} = 45$ Vdc, $V_{BE} = 1.5$ Vdc, $T_C = 150°C$)			—	5.0	
Emitter Cutoff Current		I_{EBO}			mAdc
($V_{BE} = 7.0$ Vdc, $I_C = 0$)	2N5322		—	0.1	
($V_{BE} = 5.0$ Vdc, $I_C = 0$)	2N5323		—	0.1	
ON CHARACTERISTICS(1)					
DC Current Gain		h_{FE}			—
($I_C = 500$ mAdc, $V_{CE} = 4.0$ Vdc)	2N5322		30	130	
	2N5323		40	250	
($I_C = 1.0$ Adc, $V_{CE} = 2.0$ Vdc)	2N5322		10	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$			Vdc
($I_C = 500$ mAdc, $I_B = 50$ mAdc)	2N5322			0.7	
	2N5323		—	1.2	
Base-Emitter On Voltage		$V_{BE(on)}$			Vdc
($I_C = 500$ mAdc, $V_{CE} = 4.0$ Vdc)	2N5322			1.1	
	2N5323		—	1.4	
SMALL-SIGNAL CHARACTERISTICS					
Small-Signal Current Gain ($I_C = 50$ mAdc, $V_{CE} = 4.0$ Vdc, f = 10 MHz)		h_{fe}	5	—	—
SWITCHING CHARACTERISTICS					
Turn-On Time ($V_{CC} = 30$ Vdc, $I_C = 500$ mAdc, $I_{B1} = 50$ mAdc)		t_{on}	—	100	ns
Turn-Off Time ($V_{CC} = 30$ Vdc, $I_C = 500$ mAdc, $I_{B1} = I_{B2} = 50$ mAdc)		t_{off}	—	1000	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

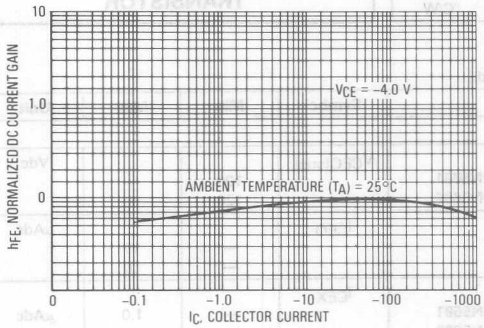
TYPICAL INPUT CHARACTERISTICS



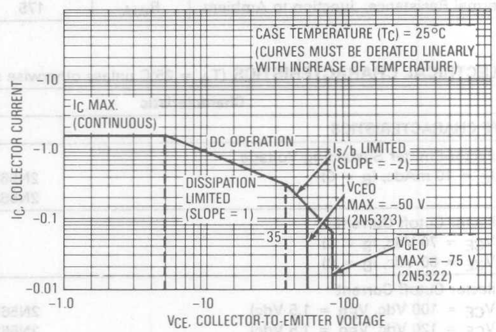
TYPICAL TRANSFER CHARACTERISTICS



CURRENT GAIN CHARACTERISTICS versus COLLECTOR-EMITTER VOLTAGE



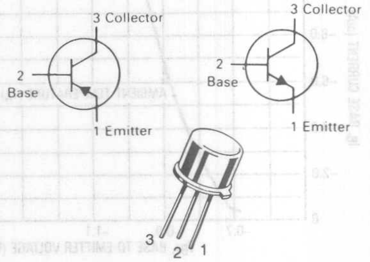
MAXIMUM SAFE OPERATING AREAS (SOA)



Rating	Symbol	2N5679 2N5681	2N5680 2N5682	Unit
Collector-Emitter Voltage	V_{CEO}	100	120	Vdc
Collector-Base Voltage	V_{CBO}	100	120	Vdc
Emitter-Base Voltage	V_{EBO}	4.0		Vdc
Base Current	I_B	0.5		Adc
Collector Current — Continuous	I_C	1.0		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 5.7		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	10 57		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

2N5680 2N5682

PNP SILICON NPN SILICON



CASE 79-02, STYLE 1
TO-39 (TO-205AD)

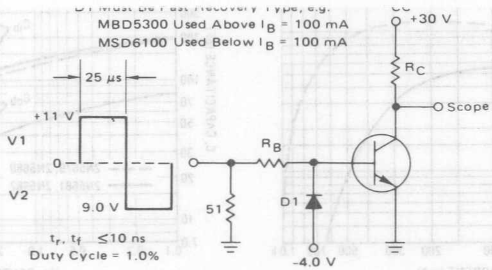
GENERAL PURPOSE TRANSISTOR

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	17.5	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	175	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage (I_C = 10 mAdc, I_B = 0)	 2N5679, 2N5681 2N5680, 2N5682	$V_{CEO(sus)}$	 100 120	 — —	Vdc
Collector Cutoff Current (V_{CE} = 70 Vdc, I_B = 0) (V_{CE} = 80 Vdc, I_B = 0)		I_{CEO}	 — —	 10 10	μAdc
Collector Cutoff Current (V_{CE} = 100 Vdc, V_{EB} = 1.5 Vdc) (V_{CE} = 120 Vdc, V_{EB} = 1.5 Vdc) (V_{CE} = 100 Vdc, V_{EB} = 1.5 Vdc, T_C = 150°C) (V_{CE} = 120 Vdc, V_{EB} = 1.5 Vdc, T_C = 150°C)	 2N5679, 2N5681 2N5680, 2N5682 2N5679, 2N5681 2N5680, 2N5682	I_{CEX}	 — — — —	 1.0 1.0 1.0 1.0	 μAdc mAdc
Collector Cutoff Current (V_{CB} = 100 Vdc, I_E = 0) (V_{CB} = 120 Vdc, I_E = 0)	 2N5679, 2N5681 2N5680, 2N5682	I_{CBO}	 — —	 1.0 1.0	μAdc
Emitter Cutoff Current (V_{EB} = 4.0 Vdc, I_C = 0)		I_{EBO}	—	1.0	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 250 mAdc, V_{CE} = 2.0 Vdc) (I_C = 1.0 Adc, V_{CE} = 2.0 Vdc)		h_{FE}	 40 5.0	 150 —	—
Collector-Emitter Saturation Voltage (I_C = 250 mAdc, I_B = 25 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc) (I_C = 1.0 Adc, I_B = 200 mAdc)		$V_{CE(sat)}$	 — — —	 0.6 1.0 2.0	Vdc
Base-Emitter Saturation Voltage (I_C = 250 mAdc, V_{CE} = 2.0 Vdc)		$V_{BE(sat)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 100 mAdc, V_{CE} = 10 Vdc, f = 10 MHz)		f_T	30	—	—
Output Capacitance (V_{CB} = 20 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	50	pF
Small-Signal Current Gain (I_C = 0.2 Adc, V_{CE} = 1.5 Vdc, f = 1.0 kHz)		h_{fe}	40	—	—



R_B and R_C Varied to Obtain Desired Current Levels

For t_d and t_r, D1 is disconnected and V2 = 0
For PNP test circuit, reverse diode and voltage polarities.

PNP
2N5679, 2N5680

NPN
2N5681, 2N5682

FIGURE 2 – TURN-ON TIME

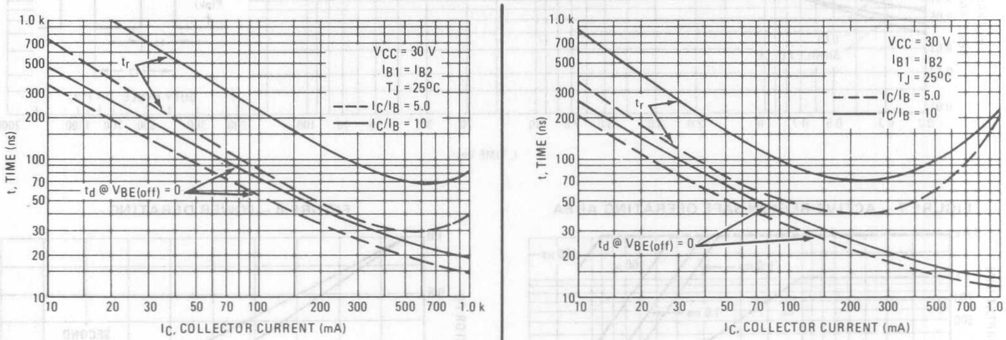
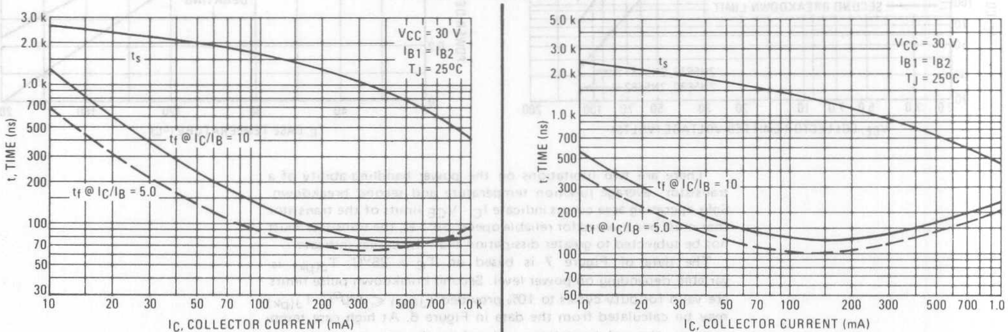


FIGURE 3 – TURN-OFF TIME



4

FIGURE 4 – CURRENT-GAIN – BANDWIDTH PRODUCT

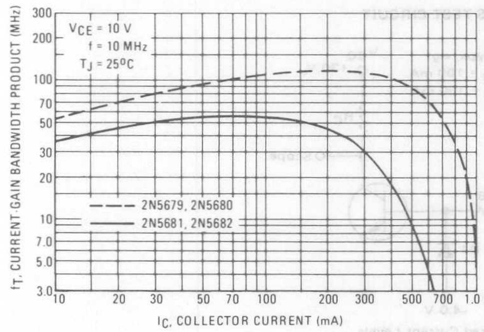


FIGURE 5 – CAPACITANCE

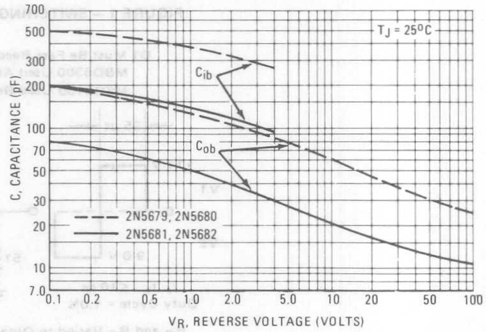


FIGURE 6 – THERMAL RESISTANCE

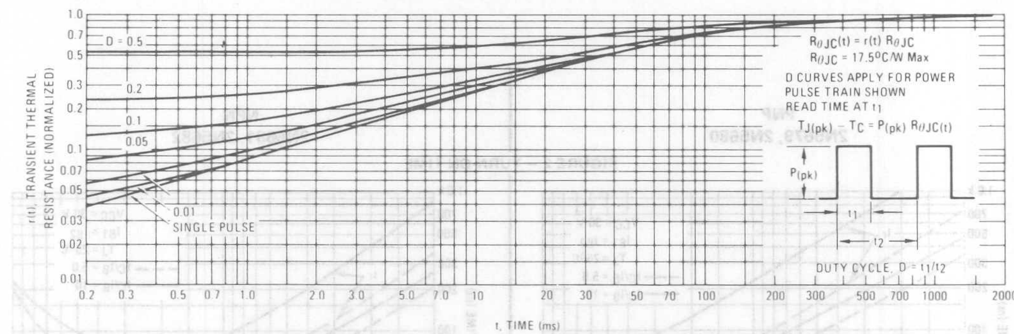


FIGURE 7 – ACTIVE-REGION SAFE OPERATING AREA

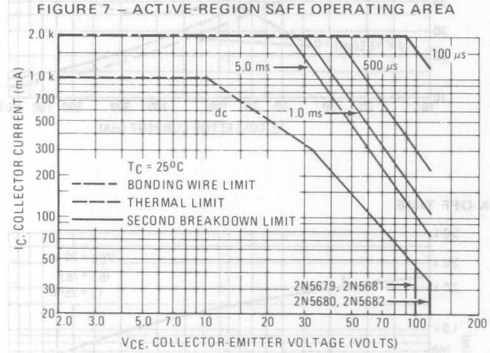
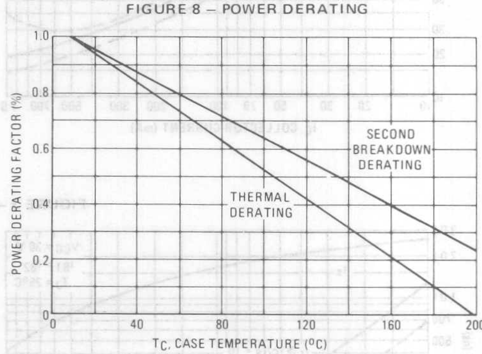


FIGURE 8 – POWER DERATING



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C \cdot V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 7 is based on T_C = 25°C; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 200°C$. $T_{J(pk)}$ may be calculated from the data in Figure 6. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Figure 7 may be found at any case temperature by using the appropriate curve on Figure 8.

PNP
2N5679, 2N5680

NPN
2N5681, 2N5682

FIGURE 9 – DC CURRENT GAIN

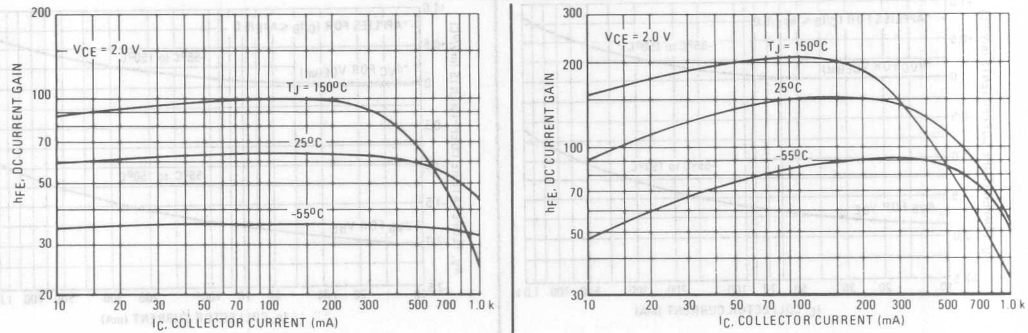


FIGURE 10 – COLLECTOR SATURATION REGION

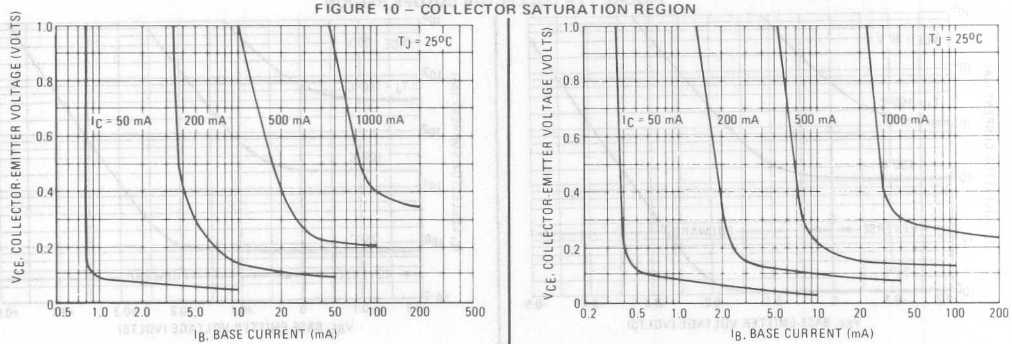
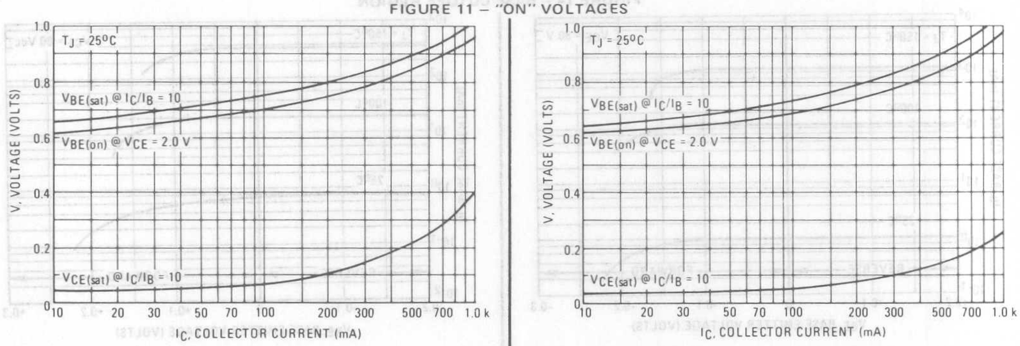


FIGURE 11 – "ON" VOLTAGES

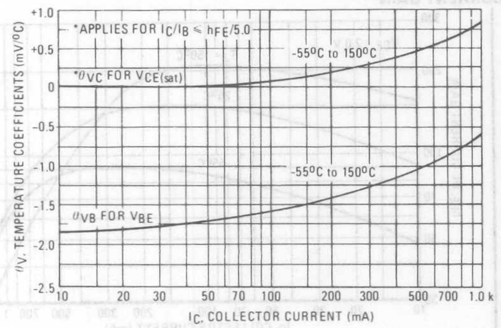


4

PNP
2N5679, 2N5680

NPN
2N5681, 2N5682

FIGURE 12 – TEMPERATURE COEFFICIENTS



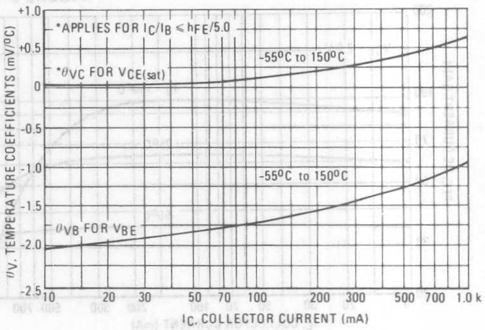
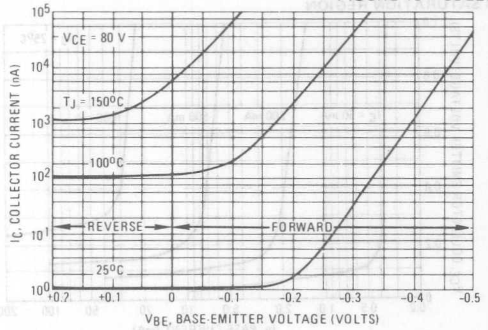


FIGURE 13 – COLLECTOR CUTOFF REGION



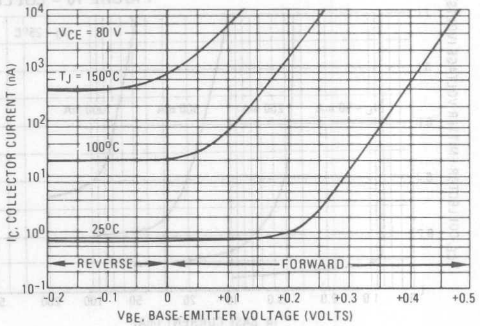
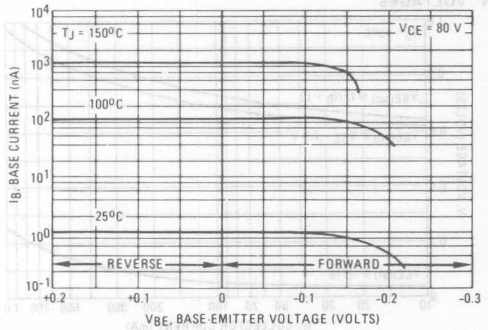
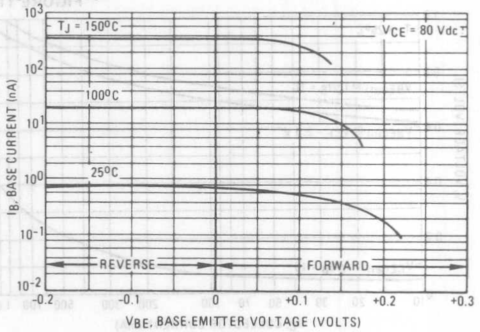


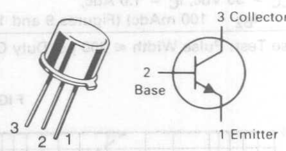
FIGURE 14 – BASE CUTOFF REGION





Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	80	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	2.0	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 6.0	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5.0 28.6	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



SWITCHING TRANSISTOR

NPN SILICON

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	175	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

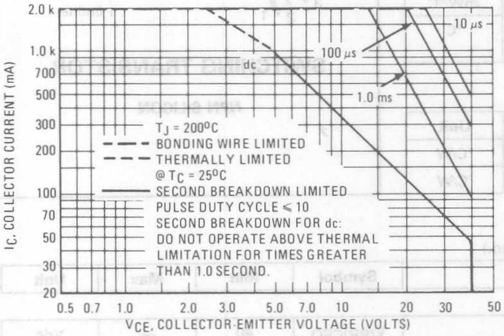
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	80	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 50$ Vdc, $V_{BE(off)} = 2.0$ Vdc) ($V_{CE} = 50$ Vdc, $V_{BE(off)} = 2.0$ Vdc, $T_A = 75°C$)	I_{CEX}	— —	0.2 5.0	μAdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$) ($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = 75°C$)	I_{CBO}	— —	0.25 5.0	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$)	I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 500$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1.0$ Adc, $V_{CE} = 1.0$ Vdc) ($I_C = 1.0$ Adc, $V_{CE} = 1.0$ Vdc, $T_A = -55°C$)	h_{FE}	30 15 10	120 100 —	—
Collector-Emitter Saturation Voltage ($I_C = 500$ mAdc, $I_B = 50$ mAdc) ($I_C = 1.0$ Adc, $I_B = 100$ mAdc)	$V_{CE(sat)}$	— —	0.4 0.7	Vdc
Base-Emitter Saturation Voltage ($I_C = 500$ mAdc, $I_B = 50$ mAdc) ($I_C = 1.0$ Adc, $I_B = 100$ mAdc)	$V_{BE(sat)}$	0.8 0.9	1.0 1.25	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	250	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{cb}	—	7.0	pF
Emitter-Base Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz)	C_{eb}	—	60	pF
SWITCHING CHARACTERISTICS				
Delay Time ($V_{CC} = 30$ Vdc, $V_{BE(off)} = 2.0$ Vdc, $I_C = 1.0$ Adc, $I_{B1} = 100$ mAdc) (Figures 8 and 10)	t_d	—	6.0	ns
Rise Time ($V_{CC} = 30$ Vdc, $V_{BE(off)} = 2.0$ Vdc, $I_C = 1.0$ Adc, $I_{B1} = 100$ mAdc) (Figures 8 and 10)	t_r	—	30	ns
Storage Time ($V_{CC} = 30$ Vdc, $I_C = 1.0$ Adc, $I_{B1} = I_{B2} = 100$ mAdc) (Figures 9 and 11)	t_s	—	35	ns
Fall Time ($V_{CC} = 30$ Vdc, $I_C = 1.0$ Adc, $I_{B1} = I_{B2} = 100$ mAdc) (Figures 9 and 11)	t_f	—	35	ns

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Turn-On Time (V_{CC} = 30 Vdc, $V_{BE(off)}$ = 2.0 Vdc, I_C = 1.0 Adc, I_{B1} = 100 mAdc) (Figures 8 and 10)	t_{on}	—	35	ns
Turn-Off Time (V_{CC} = 30 Vdc, I_C = 1.0 Adc, I_{B1} = I_{B2} = 100 mAdc) (Figures 9 and 11)	t_{off}	—	60	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 – ACTIVE-REGION SAFE OPERATING AREA



There are two limitations on the power handling ability of a transistor: junction temperature and second breakdown. Safe operating area curves indicate I_C–V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on $T_{J(pk)}$ = 200°C; T_C is variable depending on conditions. Pulse curves are valid for duty cycles of 10% provided $T_{J(pk)} \leq 200°C$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

TYPICAL DC CHARACTERISTICS

FIGURE 2 – DC CURRENT GAIN

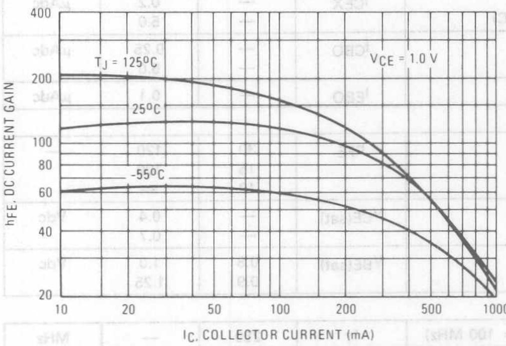


FIGURE 3 – "ON" VOLTAGES

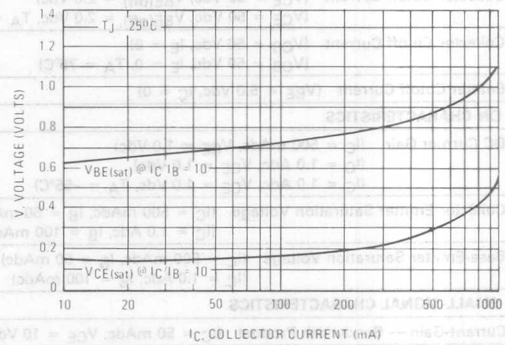


FIGURE 4 – COLLECTOR SATURATION REGION

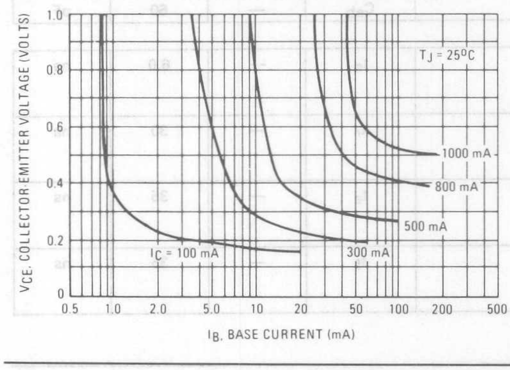
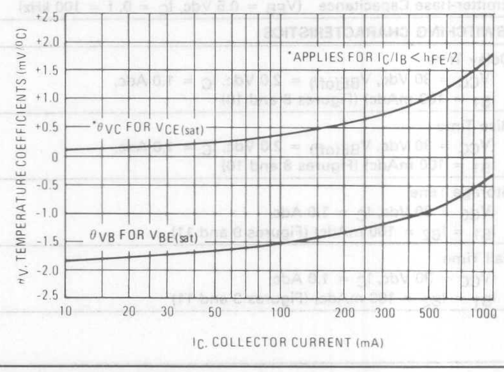


FIGURE 5 – TEMPERATURE COEFFICIENTS



TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 6 – CURRENT-GAIN–BANDWIDTH PRODUCT

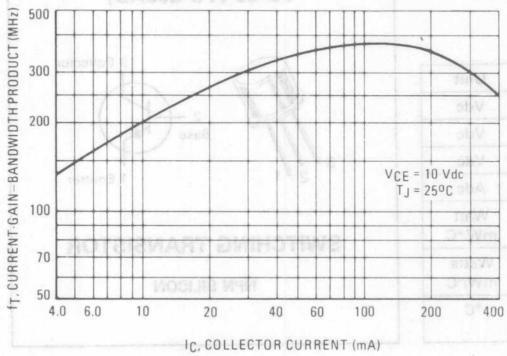


FIGURE 7 – CAPACITANCE

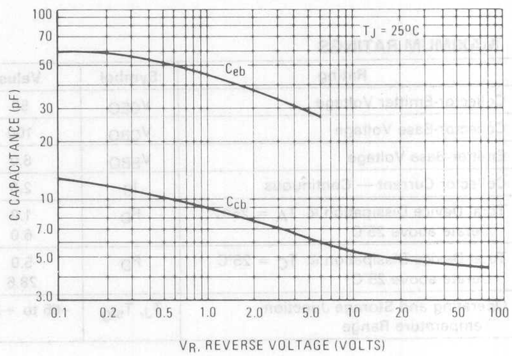


FIGURE 8 – TURN-ON TIME

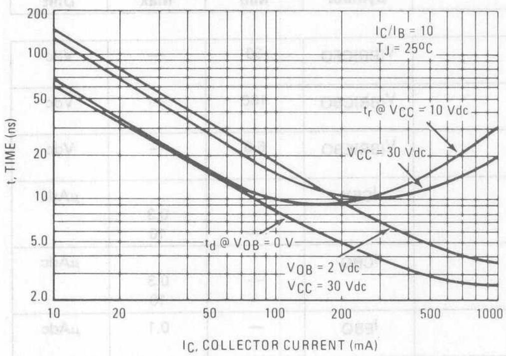


FIGURE 9 – TURN-OFF TIME

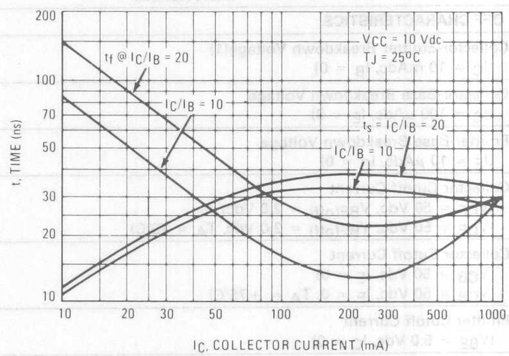


FIGURE 10 – TURN-ON TIME TEST CIRCUIT

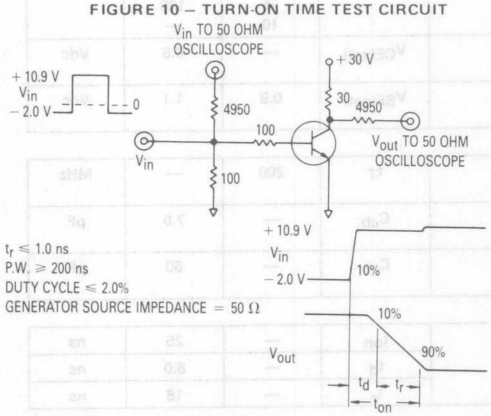
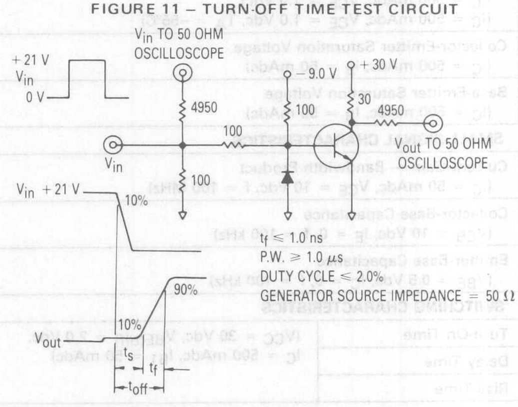


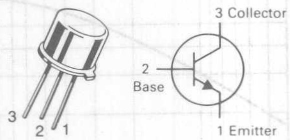
FIGURE 11 – TURN-OFF TIME TEST CIRCUIT



ALL WAVEFORMS AND BIAS LEVELS MUST BE SET WITH UNIT IN CIRCUIT.

ALL WAVEFORMS AND BIAS LEVELS MUST BE SET WITH UNIT IN CIRCUIT.

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



SWITCHING TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector-Base Voltage	V_{CBO}	100	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	2.0	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 6.0	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5.0 28.6	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	50	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	100	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 50$ Vdc, $V_{BE(off)} = 2.0$ Vdc) ($V_{CE} = 50$ Vdc, $V_{BE(off)} = 2.0$ Vdc, $T_A = 75°C$)	I_{CEX}	 — —	 0.3 10	μAdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$) ($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = +75°C$)	I_{CBO}	 — —	 0.3 10	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$)	I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS(1)				
DC Current Gain ($I_C = 500$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 500$ mAdc, $V_{CE} = 1.0$ Vdc, $T_A = -55°C$)	h_{FE}	 25 10	 100 —	—
Collector-Emitter Saturation Voltage ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	$V_{BE(sat)}$	0.8	1.1	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	200	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{cb}	—	7.0	pF
Emitter-Base Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz)	C_{eb}	—	60	pF

SWITCHING CHARACTERISTICS

Characteristic	Conditions	Symbol	Min	Max	Unit
Turn-On Time	($V_{CC} = 30$ Vdc, $V_{BE(off)} = 2.0$ Vdc, $I_C = 500$ mAdc, $I_{B1} = 50$ mAdc)	t_{on}	—	25	ns
Delay Time		t_d	—	8.0	ns
Rise Time		t_r	—	18	ns

Storage Time	$I_{B1} = I_{B2} = 50$ mAdc)	t_s	—	35	ns
Fall Time		t_f	—	35	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 1 – CURRENT-GAIN–BANDWIDTH PRODUCT

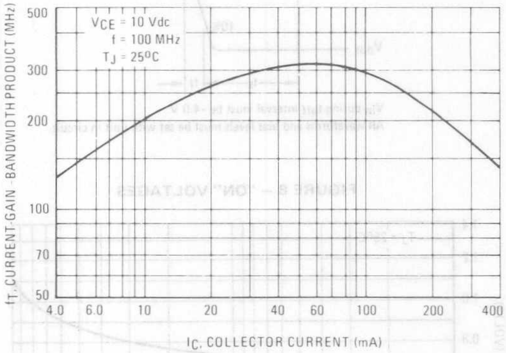


FIGURE 2 – CAPACITANCE

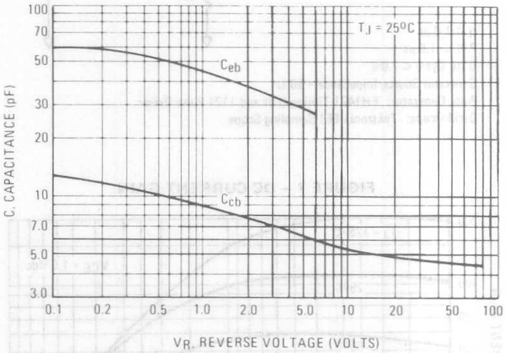


FIGURE 3 – TURN-ON TIME

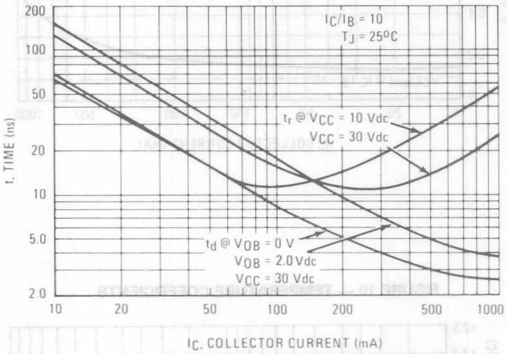


FIGURE 4 – TURN-OFF TIME

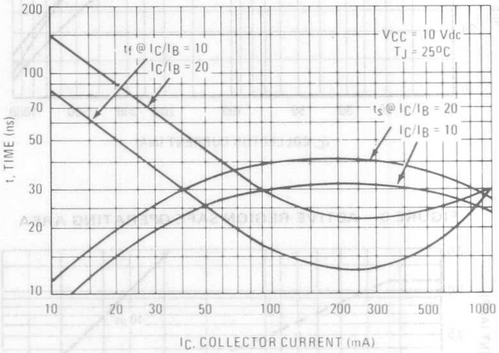
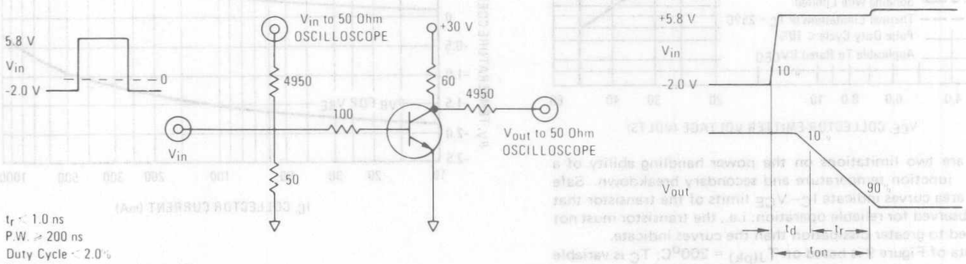


FIGURE 5 – TURN-ON TIME TEST CIRCUIT



t_r ≤ 1.0 ns
P.W. ≥ 200 ns
Duty Cycle ≤ 2.0%
Generator Source Impedance = 50 Ω
Pulse Generator: EH1421 Timing Unit and 1121 Pulse Driver
Oscilloscope: Tektronix 661 Sampling Scope

V_{in} during t_{on} interval must be +5.8 V.
All waveforms and bias levels must be set with unit in circuit.

FIGURE 6 – TURN-OFF TIME TEST CIRCUIT

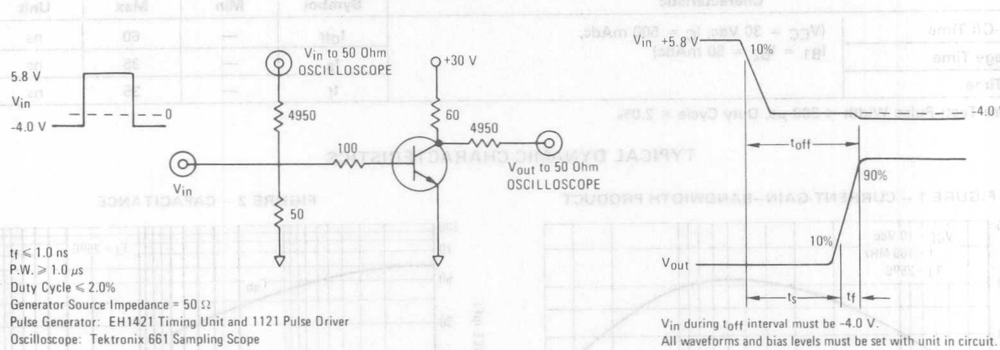


FIGURE 7 – DC CURRENT GAIN

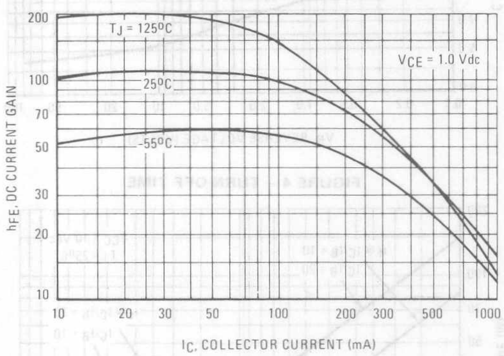


FIGURE 8 – "ON" VOLTAGES

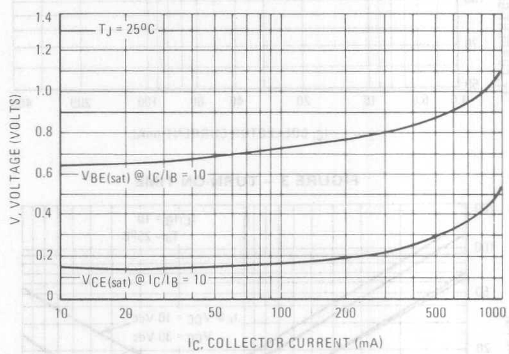


FIGURE 9 – ACTIVE-REGION SAFE OPERATING AREA

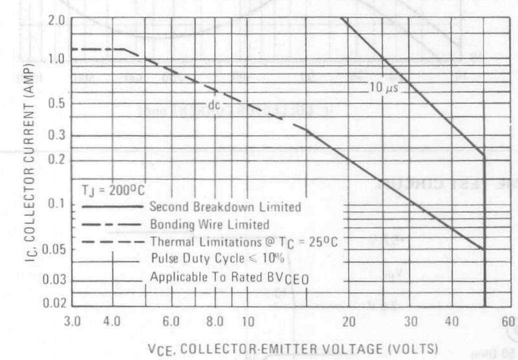
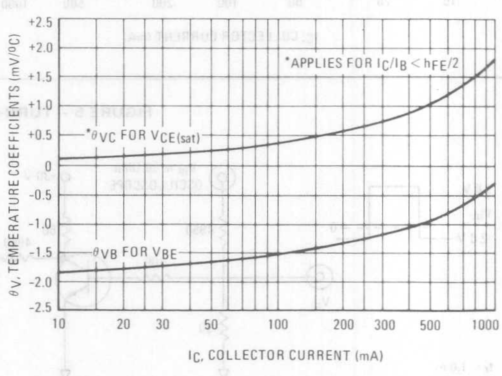


FIGURE 10 — TEMPERATURE COEFFICIENTS

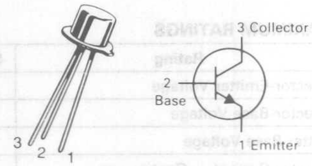


There are two limitations on the power handling ability of a transistor: junction temperature and secondary breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 9 is based on $T_{J(pk)} = 200°C$; T_C is variable depending on conditions. Pulse curves are valid for duty cycles of 10% provided $T_{J(pk)} \leq 200°C$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by secondary breakdown.

2N6430
2N6431

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	2N6430	2N6431	Unit
Collector-Emitter Voltage	V_{CEO}	200	300	Vdc
Collector-Base Voltage	V_{CBO}	200	300	Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	50		mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	500 2.86		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.8 10.3		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

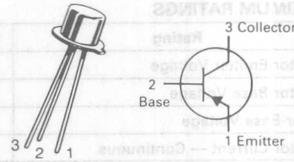
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	2N6430 2N6431	$V_{(BR)CEO}$	200 300	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.1$ mAdc, $I_E = 0$)	2N6430 2N6431	$V_{(BR)CBO}$	200 300	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 0.1$ mAdc, $I_C = 0$)		$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 160$ Vdc) ($V_{CB} = 200$ Vdc)	2N6430 2N6431	I_{CBO}	— —	0.1 0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 4.0$ Vdc, $I_C = 0$)		I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 30$ mAdc, $V_{CE} = 10$ Vdc)		h_{FE}	25 40 50	— — 200	—
Collector-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)		$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)		$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)		f_T	50	500	MHz
Collector-Base Capacitance ($V_{CB} = 20$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{cb}	—	4.0	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2N6432
2N6433

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

Refer to 2N3743 for graphs.

MAXIMUM RATINGS

Rating	Symbol	2N6432	2N6433	Unit
Collector-Emitter Voltage	V_{CEO}	200	300	Vdc
Collector-Base Voltage	V_{CBO}	200	300	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	500 2.86		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.8 10.3		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

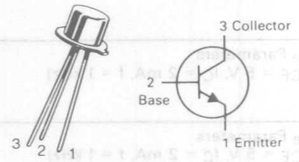
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	 2N6432 2N6433	$V_{(BR)CEO}$	 200 300	 — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.1$ mAdc, $I_E = 0$)	 2N6432 2N6433	$V_{(BR)CBO}$	 200 300	 — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 0.1$ mAdc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 160$ Vdc) ($V_{CB} = 200$ Vdc)	 2N6432 2N6433	I_{CBO}	 — —	 0.25 0.25	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)		I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 30$ mAdc, $V_{CE} = 10$ Vdc)		h_{FE}	 25 40 30	 — — 150	—
Collector-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)		$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)		$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 20 MHz)		f_T	50	500	MHz
Collector-Base Capacitance ($V_{CB} = 20$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{cb}	—	6.0	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

BC109,A,B,C

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



TRANSISTOR

NPN SILICON

4

MAXIMUM RATINGS

Rating	Symbol	BC 107	BC 108	BC 109	Unit
Collector-Emitter Voltage	V_{CEO}	45	25	25	Vdc
Collector-Base Voltage	V_{CBO}	50	30	30	Vdc
Emitter-Base Voltage	V_{EBO}	6	5	5	Vdc
Collector Current − Continuous	I_C		0.2		Amp
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D		0.6 2.28		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ $T_C = 100°C$ Derate above 25°C	P_D		1 6.67		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	175	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector Base Leakage Current		I_{CBO}				
($I_E = 0$, $V_{CB} = 45$ V)	BC107				15	nA
($I_E = 0$, $V_{CB} = 45$ V, $T_{Amb} = 125°C$)	BC107				4	μA
($I_E = 0$, $V_{CB} = 25$ V)	BC108/109				15	nA
($I_E = 0$, $V_{CB} = 25$ V, $T_{Amb} = 125°C$)	BC108/109				4	μA
Emitter Base Breakdown Voltage		$V_{(BR)EBO}$				V
($I_E = 10$ μA, $I_C = 0$)	BC107		6			
	BC108/109		5			
Collector Emitter Breakdown Voltage		$V_{(BR)CEO}$				V
($I_C = 2$ mA, $I_E = 0$)	BC107		45			
	BC108/109		25			
ON CHARACTERISTICS						
DC Current gain		h_{FE}				
($V_{CE} = 5$ V, $I_C = 2$ mA)	BC107		110		450	
	BC108		110		800	
	BC109		200		800	
	A group		110		220	
	B group		200		450	
	C group		420		800	
($V_{CE} = 5$ V, $I_C = 10$ μA)	B group		40			
	C group		100			
Base Emitter Saturation Voltage		$V_{BE(sat)}$				V
($I_C = 10$ mA, $I_B = 0.5$ mA)				0.7	0.83	
($I_C = 100$ mA, $I_B = 5$ mA)				1.0	1.05	
Collector Emitter Saturation Voltage		$V_{CE(sat)}$				V
($I_C = 10$ mA, $I_B = 0.5$ mA)					0.25	
($I_C = 100$ mA, $I_B = 5$ mA)					0.60	
Base Emitter on Voltage		$V_{BE(on)}$				V
($I_C = 2$ mA, $V_{CE} = 5$ V)			0.55		0.70	
($I_C = 10$ mA, $V_{CE} = 5$ V)					0.77	
Collector Knee Voltage		$V_{CE(K)}$				V
($I_C = 10$ mA, I_B = the value for which $I_C = 11$ mA at $V_{CE} = 1$ V)				0.4	0.6	
DYNAMIC CHARACTERISTICS						
Transition Frequency		f_T				MHz
($I_C = 10$ mA, f = 100 MHz, $V_{CE} = 5$ V)			150	300		
Noise Figure		NF				dB
($V_{CE} = 5$ V, $I_C = 0.2$ mA, $R_g = 2$ KΩ)						
F = 30 Hz to 15 kHz	BC109				4	
F = 1 kHz, ΔF = 200 Hz	BC109				4	
	BC107/108				10	

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
Output Capacitance (V_{CB} = 10 V, f = 1 MHz)		C_{obo}			4.5	pF
h_{21e} Parameters (V_{CE} = 5 V, I_C = 2 mA, f = 1 kHz)	BC107/108	h_{21e}	125		500	
	BC109		240		900	
	A group		125		260	
	B group		240		500	
	C group		450		900	
h_{11e} Parameters (V_{CE} = 5 V, I_C = 2 mA, f = 1 kHz)	A group	h_{11e}	1.6		4.5	kΩ
	B group		3.2		8.5	
	C group		6.0		15	
h_{22e} Parameters (V_{CE} = 5 V, I_C = 2 mA, f = 1 kHz)	A group	h_{22e}			30	μhos
	B group				60	
	C group				110	

FIGURE 1 – EMITTER-BASE CAPACITANCE COLLECTOR-BASE CAPACITANCE

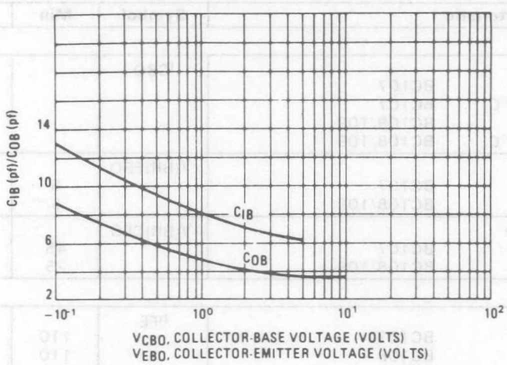


FIGURE 2 – CURRENT GAIN – BANDWIDTH PRODUCT

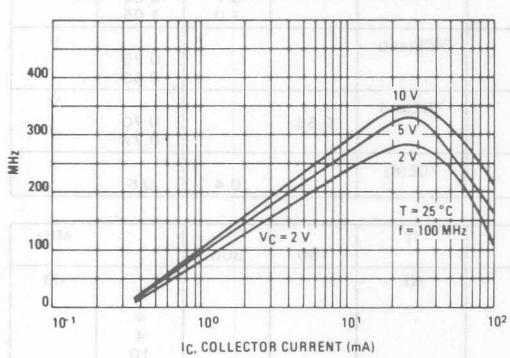
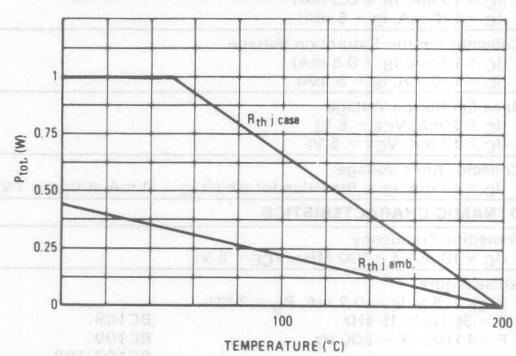
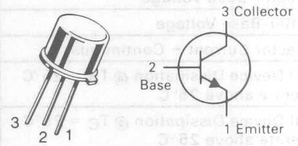


FIGURE 3 – TOTAL PERMISSIBLE POWER DISSIPATION



BC140,10,16
BC141,10,16

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N3019 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BC 140	BC 141	Unit
Collector-Emitter Voltage	V_{CEO}	40	60	Vdc
Collector-Base Voltage	V_{CBO}	80	100	Vdc
Emitter-Base Voltage	V_{EBO}	7		Vdc
Collector Current − Continuous	I_C	1		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.8 4.6		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	3.7 20		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

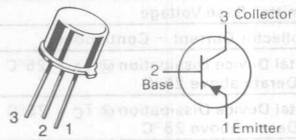
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector Cutoff Current ($I_E = 0$, $V_{CE} = 60$ V)	 $T_A = 150°C$	I_{CES}		100 100	nA µA
Collector-Emitter Breakdown Voltage ($I_{CES} = 100$ µA, $I_E = 0$)	BC140 BC141	$V_{(BR)CES}$	80 100		V
Collector-Emitter Breakdown Voltage(1) ($I_C = 30$ mA, $I_B = 0$)	 BC140 BC141	$V_{(BR)CEO}$	 40 60		V
Emitter-Base Breakdown Voltage ($I_E = 100$ µA, $I_C = 0$)		$V_{(BR)EBO}$	7		V
ON CHARACTERISTICS					
DC Current Gain(1) ($I_C = 100$ mA, $V_{CE} = 1$ V)	for BC140, 141 for BC140, 141 Group 10 for BC140, 141 Group 16	h_{FE}	40 63 100	400 160 250	
Collector-Emitter Saturation Voltage(1) ($I_C = 1$ A, $I_B = 0.1$ A)		$V_{CE(sat)}$		1	V
Base-Emitter Voltage(1) ($I_C = 1$ A, $V_{CE} = 1$ V)		$V_{BE(on)}$		2	V
SMALL SIGNAL CHARACTERISTICS					
Gain Bandwidth Product ($I_C = 50$ mA, $V_{CE} = 10$ V, f = 20 MHz)		f_T	50		MHz
Input Capacitance ($V_{EB} = 0{,}5$ V, $I_C = 0$, f = 1 MHz)		C_{ib}		80	pF
Capacitance ($I_E = 0$, $V_{CB} = 10$ V, f = 1 MHz)		C_{ob}		25	pF
Turn On Time ($I_C = 150$ mA, $I_{B1} = 7.5$ mA)		t_{on}		250	ns
Turn Off Time ($I_C = 150$ mA, $I_{B1} = I_{B2} = 7.5$ mA)		t_{off}		850	ns

(1) Pulsed: Pulse Duration = 300 µs, Duty Cycle = 1%.

BC160,-6,10,16
BC161,-6,10,16

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



AMPLIFIER TRANSISTOR

PNP SILICON

Refer to 2N4033 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BC 160	BC 161	Unit
Collector-Emitter Voltage	V_{CEO}	40	60	Vdc
Collector-Base Voltage	V_{CBO}	40	60	Vdc
Emitter-Base Voltage	V_{EBO}	5		Vdc
Collector Current – Continuous	I_C	1		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.8 4.6		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	3.7 20		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector Cutoff Current	I_{CES}			
$I_E = 0$, $V_{CES} = -40$ V for BC160			−100	nA
$V_{CES} = -60$ V for BC161			−100	
$V_{CES} = -40$ V for BC160 $T_{Amb} = 150°C$			−100	μA
$V_{CES} = -60$ V for BC161 $T_{Amb} = 150°C$			−100	
Collector Emitter Breakdown Voltage	$V_{(BR)CES}$			V
$I_C = -100$ μA, $I_E = 0$ for BC160		−40		
for BC161		−60		
Collector-Emitter Breakdown Voltage(1)	$V_{(BR)CEO}$			V
$I_C = -10$ mA, $I_B = 0$ for BC160		−40		
for BC161		−60		
Emittor-Base Breakdown Voltage $I_E = -100$ μA, $I_C = 0$	$V_{(BR)EBO}$	−5		V
ON CHARACTERISTICS				
DC Current Gain(1) $I_C = -100$ mA, $V_{CE} = -1$ V	h_{FE}			
for BC160, BC161		40	400	
for BC160, BC161 Group 6		40	100	
for BC160, BC161 Group 10		63	160	
for BC160, BC161 Group 16		100	250	
Collector-Emitter Saturation Voltage(1) ($I_C = -1$ A, $I_B = -0.1$ A)	$V_{CE(sat)}$		−1	V
Base-Emitter Voltage(1) ($I_C = -1$ A, $V_{CE} = -1$ V)	$V_{BE(on)}$		−1.7	V
SMALL SIGNAL CHARACTERISTICS				
Gain Bandwidth Product ($I_C = -50$ mA, $V_{CE} = -10$ V, f = 20 MHz	f_T	50		MHz
Input Capacitance ($V_{EB} = -10$ V, f = 1 MHz)	C_{ib}		180	pF
Output Capacitance ($V_{CB} = -10$ V, $I_E = 0$, f = 1 MHz)	C_{obo}		30	pF
Turn On Time ($I_C = -100$ mA, $I_{B1} = -5$ μA)	T_{on}		500	ns
Turn Off Time ($I_C = -100$ mA, $I_{B1} = I_{B2} = -5$ μA)	T_{off}		650	ns

(1) Pulsed: Pulse Duration = 300 μs, Duty Cycle = 1%.

MAXIMUM RATINGS

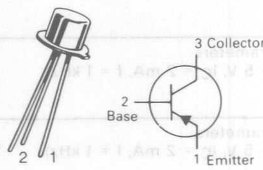
Rating	Symbol	BC 177	BC 178	BC 179	Unit
Collector-Emitter Voltage	V_{CEO}	45	25	20	Vdc
Collector-Emitter Voltage	V_{CES}	50	30	25	Vdc
Collector-Base Voltage	V_{CBO}	50	30	25	Vdc
Emitter-Base Voltage	V_{EBO}	5			Vdc
Collector Current − Continuous	I_C	0.2			Amp
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.6 2.28			Watt mW/°C
Total Device Dissipation @ T_C = 25°C T_C = 100°C Derate above 25°C	P_D	1 6.67			Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	175	°C/W

BC177,A,B,C
BC178,A,B,C
BC179,A,B,C

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



TRANSISTOR

PNP SILICON

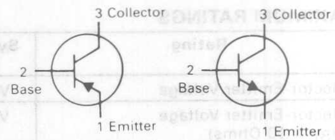
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector Emitter Leakage Current (V_{CE} = 20 V, I_E = 0) (V_{CE} = 20 V, I_E = 0, T_{Amb} = 125°C)		I_{CES}			 100 4	 nA μA
Collector Base Breakdown Voltage (I_C = 10 μA)	BC177 BC178 BC179	$V_{(BR)CBO}$	50 30 25			V
Collector Emitter Breakdown Voltage (I_C = 2 mA, I_E = 0)	BC177 BC178 BC179	$V_{(BR)CEO}$	45 25 20			V
Emitter Base Breakdown Voltage (I_E = 10 μA, I_C = 0)		$V_{(BR)EBO}$	5			V
ON CHARACTERISTICS						
DC Current Gain (I_C = 2 mA, V_{CE} = 5 V)	BC177 BC178 BC179 A Group B Group C Group	h_{FE}	120 120 180 120 180 380		460 800 800 220 460 800	
Collector Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5 mA)		$V_{CE(sat)}$			 0.2 0.6	V
Base Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5 mA)		$V_{BE(sat)}$		 0.7 0.9	 0.8	V
Base Emitter on Voltage (I_C = 2 mA, V_{CE} = 5 V)		$V_{BE(on)}$	 0.6		 0.75	V
Collector Knee Voltage (I_C = 10 mA, I_B = the value for which (I_C = 11 mA, at V_{CE} = 1V)		$V_{CE(K)}$		 0.4	 0.6	V
DYNAMIC CHARACTERISTICS						
Transition Frequency (V_{CE} = 5 V, I_C = 10 mA, f = 50 MHz)		f_T	 200	 300		MHz
Noise Figure (V_{CE} = 5 V, I_C = 0.2 mA, R_g = 2 KΩ) F = 30 Hz to 15 kHz F = 1 kHz, F = 200 Hz	 BC179 BC179 BC177/178	NF			 4 4 10	dB

Characteristic		Symbol	Min	Typ	Max	Unit
Output Capacitance (V_{CB} = 10 V, f = 1 MHz)		C_{obo}		3.5	4	pF
h_{21e} Parameters (V_{CE} = 5 V, I_C = 2 mA, f = 1 kHz)	BC177	h_{21e}	125		500	
	BC178		125		900	
	BC179		240		900	
	A Group		125		260	
	B Group		240		500	
	C Group		450		900	
h_{11e} Parameters (V_{CE} = 5 V, I_C = 2 mA, f = 1 kHz)	A Group	h_{11e}	1.6		4.5	KΩ
	B Group		3.2		8.5	
	C Group		6.0		15.0	
h_{22e} Parameters (V_{GE} = 5 V, I_C = 2 mA, f = 1 kHz)	A Group	h_{22e}			30	μmhos
	B Group				60	
	C Group				110	

BC393 BC394

PNP NPN



CASE 22-03, STYLE 1
TO-18 (TO-206AA)

HIGH VOLTAGE TRANSISTOR

4

MAXIMUM RATINGS

Rating	Symbol	BC 393	BC 394	Unit
Collector-Emitter Voltage	V_{CEO}	180	180	Vdc
Collector-Base Voltage	V_{CBO}	180	180	Vdc
Emitter-Base Voltage	V_{EBO}	6	6	Vdc
Collector Current — Continuous	I_C	0.5		Amp
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.4 2.66		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ $T_C = 100°C$ Derate above 25°C	P_D	1.5 10.0		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W

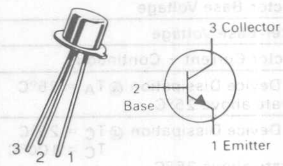
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 10$ mA, $I_B = 0$)	$V_{(BR)CEO}$	180			Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	180			Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	6			Vdc
Collector Cutoff Current ($V_{CB} = 100$ V, $I_E = 0$)	I_{CBO}			50	nA
Collector-Emitter Cutoff ($V_{CE} = 100$ V, $I_B = 0$) ($T_{Amb} = 150°C$)	I_{CEO}			50	μA
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 10$ mA, $V_{CE} = 10$ V)	h_{FE}	50	100		
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1$ mAdc)	$V_{CE(sat)}$		0.15	0.3	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1$ mAdc)	$V_{BE(sat)}$		0.7	0.9	Vdc
DYNAMIC CHARACTERISTICS					
Current Gain Bandwidth Product ($I_C = 20$ mAdc, $V_{CE} = 20$ Vdc, f = 20 MHz)	f_T	50	110	200	MHz
Output Capacitance ($I_E = 0$, $V_{CB} = 20$ Vdc, f = 1 MHz)	C_{obo}	—	3.5	7	pF
Input Capacitance ($I_C = 0$, $V_{EB} = 0.5$ Vdc, f = 1 MHz)	C_{ib}	—	75	—	pF
Turn-On Time ($I_{B1} = 10$ mA, $I_C = 50$ mAdc, $V_{CC} = 100$ Vdc))	t_{on}	—	100	—	ns
Turn-Off Time ($I_{B2} = 10$ mAdc, $I_C = 50$ mAdc, $V_{CC} = 100$ Vdc))	t_{off}	—	400	—	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

BCY58,-VII,VIII,IX,X
BCY59,-VII,VIII,IX,X

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	BCY 58	BCY 59	Unit
Collector-Emitter Voltage	V_{CEO}	32	45	Vdc
Collector-Emitter Voltage (R_{BE} = 10 Ohms)	V_{CES}	32	45	Vdc
Emitter-Base Voltage	V_{EBO}	7		Vdc
Collector Current — Continuous	I_C	0.2		Amp
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.6 2.28		Watt mW/°C
Total Device Dissipation @ T_C = 25°C T_C = 100°C Derate above 25°C	P_D	1 6.67		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	150	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	450	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Type	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_C = 0)	BCY58 BCY59	$V_{(BR)CEO}$	32 45			Vdc
Emitter-Base Breakdown Voltage (I_E = 1µAdc, I_C = 0)	all	$V_{(BR)EBO}$	7			Vdc
Collector Cutoff Current						
(V_{CE} = 32 V)	BCY58	I_{CES}		0.2	10	nAdc
(V_{CE} = 45 V)	BCY59			0.2	10	
(V_{CE} = 32 V, T_A = 100°C, V_{BE} = 0.2 V)	BCY58	I_{CEX}			20	µAdc
(V_{CE} = 45 V, T_A = 100°C, V_{BE} = 0.2 V)	BCY59				20	
(V_{CE} = 32 V, T_A = 150°)	BCY58	I_{CES}		0.2	10	µAdc
(V_{CE} = 45 V, T_A = 150°)	BCY59			0.5	10	
Emitter Base Cutoff Current (V_{EB} = 5 V)	all	I_{EBO}			10	nAdc
ON CHARACTERISTICS						
DC Current Gain		h_{FE}				
(I_C = 10 µAdc, V_{CE} = 5 Vdc)	BCY59-VII, BCY58-VII					
	BCY59-VIII, BCY58-VIII		20	145		
	BCY59-IX, BCY58-IX		40	220		
	BCY59-X, BCY58-X		100	300		
(I_C = 2 mAdc, V_{CE} = 5 Vdc)	BCY59-VII, BCY58-VII		120	170	220	
	BCY59-VIII, BCY58-VIII		180	250	310	
	BCY59-IX, BCY58-IX		250	350	460	
	BCY59-X, BCY58-X		380	500	630	
(I_C = 10 mAdc, V_{CE} = 1 Vdc)	BCY59-VII, BCY58-VII		80	190		
	BCY59-VIII, BCY58-VIII		120	260	400	
	BCY59-IX, BCY58-IX		160	380	630	
	BCY59-X, BCY58-X		240	550	1000	
(I_C = 100 mAdc, V_{CE} = 1 Vdc)	BCY59-VII, BCY58-VII		40			
	BCY59-VIII, BCY58-VIII		45			
	BCY59-IX, BCY58-IX		60			
	BCY59-X, BCY58-X		60			
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 2.5 mAdc) (I_C = 10 mAdc, I_B = 0.25 mA)	all	$V_{CE(sat)}$	0.15 0.05	0.30 0.12	0.70 0.35	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.25 mA) (I_C = 100 mA, I_B = 2.5 mA)	all	$V_{BE(sat)}$	0.6 0.75	0.70 0.90	0.85 1.2	Vdc
Base-Emitter on Voltage (I_C = 2 mAdc, V_{CE} = 5 Vdc)	all	$V_{BE(on)}$	0.55	0.62	0.70	Vdc

Characteristic	Type	Symbol	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5 V, f = 100 MHz)	all	f_T	125	200		MHz
Output Capacitance (V_{CE} = 10 Vdc, I_C = 0, f = 1 MHz)	all	C_{ob}		3.5	6	pF
Input Capacitance (V_{BE} = 0.5 V, I_C = 0, f = 1 MHz)	all	C_{ib}		8	15	pF
Small Signal Current Gain (I_C = 2 mAdc, V_{CE} = 5 Vdc, f = 1 kHz)	BCY58-VII, BCY59-VII BCY58-VIII, BCY59-VIII BCY58-IX, BCY59-IX BCY58-X, BCY59-X	h_{fe} (h_{21e})	125 175 250 350	200 260 330 520	250 350 500 700	
Output Admittance (I_C = 2 mAdc, V_{CE} = 5 Vdc, f = 1 kHz)	BCY58-VII, BCY59-VII BCY58-VIII, BCY59-VIII BCY58-IX, BCY59-IX BCY58-X, BCY59-X	h_{oe} (h_{22e})			30 50 60 100	μmhos
Input Impedance (I_C = 2 mAdc, V_{CE} = 5 Vdc, f = 1 kHz)	BCY58-VII, BCY59-VII BCY58-VIII, BCY59-VIII BCY58-IX, BCY59-IX BCY58-X, BCY59-X	h_{ie} (h_{11e})	1.6 2.5 3.2 4.5		4.5 6 8.5 12	Kohms
Voltage Feedback Ratio (I_C = 2 mAdc, V_{CE} = 5 Vdc, f = kHz)	BCY58-VII, BCY59-VII BCY58-VIII, BCY59-VIII BCY58-IX, BCY59-IX BCY58-X, BCY59-X	h_{re} (h_{12e})		1.5 2 2 3		$\times 10^{-4}$
Noise Figure (I_C = 0.2 mAdc, V_{CE} = 5 Vdc, R_S = 2 Kohms, f = 1 kHz)	all	N_F		2	6	dB
SWITCHING CHARACTERISTICS						
I_C = 10 mA, I_{B1} = 1 mA, I_{B2} = 1 mA V_{BB} = 3.6 V, R_1 = R_2 = 5 KΩ. R_L = 990 ohms * See test circuit.		t_d t_r t_{on} t_s t_f t_{off}		35 50 85 400 80 480	 150 800	nS
I_C = 100 mA, I_{B1} = 10 mA, I_{B2} = 10 mA V_{BB} = 5 V, R_1 = 500 Ω, R_2 = 700 Ω R_L = 98 ohms * See test circuit.		t_d t_r t_{on} t_s t_f t_{off}		5 50 55 250 200 450	 150 800	nS

TEST CIRCUIT

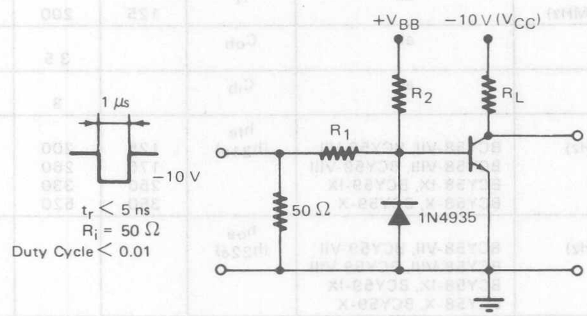


FIGURE 1 – CURRENT GAIN (BCY58-VII/BCY59-VII)

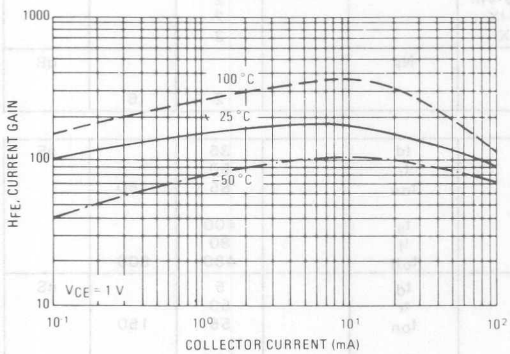


FIGURE 2 – CURRENT GAIN (BCY58-VIII/BCY59-VIII)

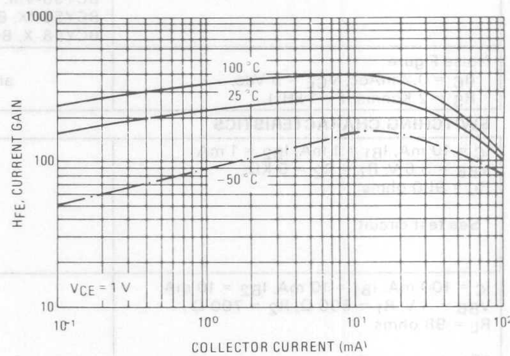


FIGURE 3 – CURRENT GAIN (BCY58-IX/BCY59-IX)

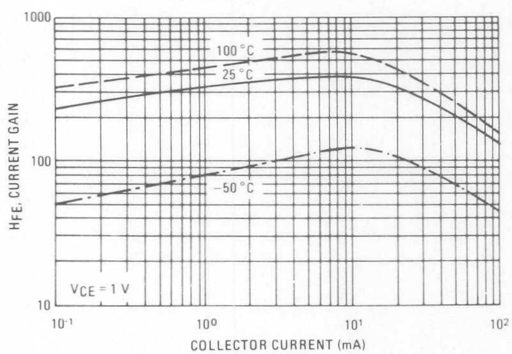


FIGURE 4 – CURRENT GAIN (BCY58-X/BCY59-X)

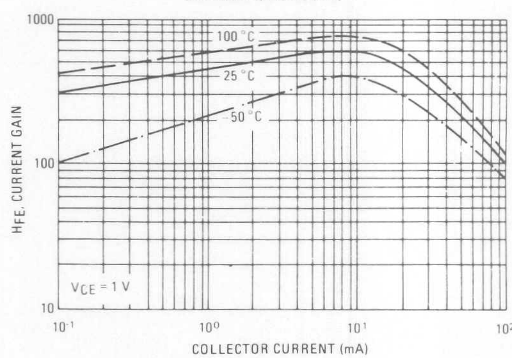


FIGURE 5 – SATURATION VOLTAGE

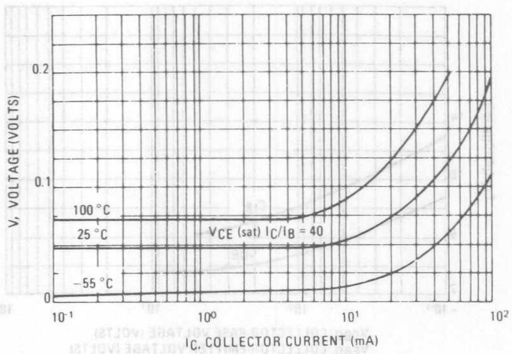


FIGURE 6 – SATURATION VOLTAGE

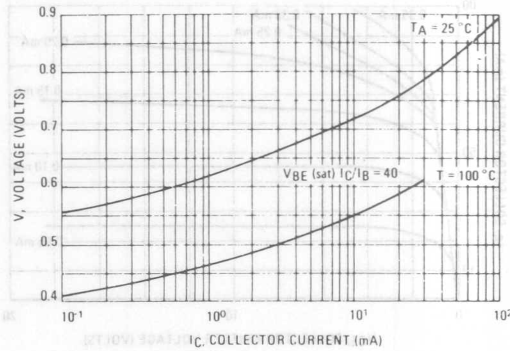


FIGURE 7 – INPUT CHARACTERISTIC (COMMON EMITTER CIRCUIT)

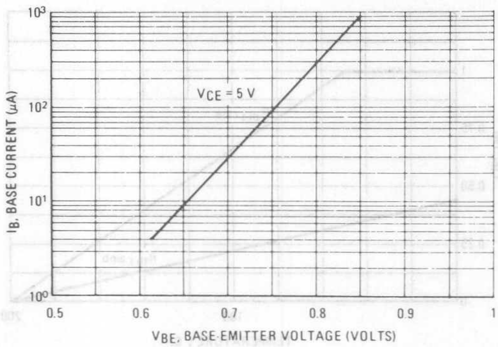


FIGURE 8 – OUTPUT CHARACTERISTIC (COMMON EMITTER CIRCUIT)

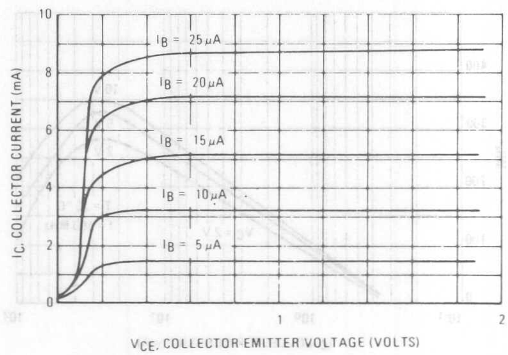


FIGURE 9 – OUTPUT CHARACTERISTIC (COMMON EMITTER CIRCUIT)

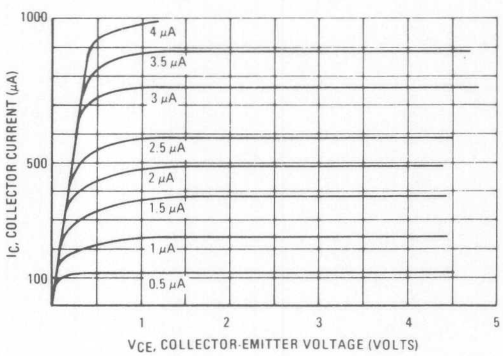
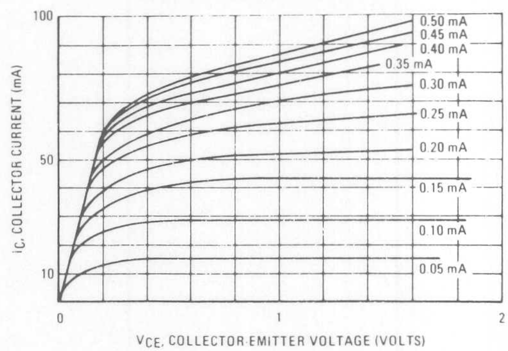
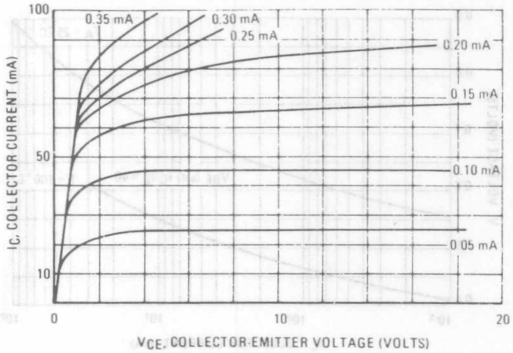


FIGURE 10 – OUTPUT CHARACTERISTIC (COMMON EMITTER CIRCUIT)





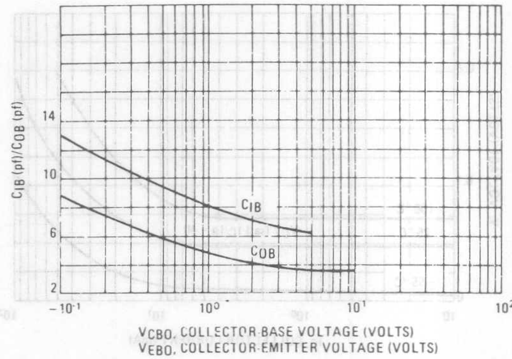


FIGURE 13 – CURRENT GAIN – BANDWIDTH PRODUCT

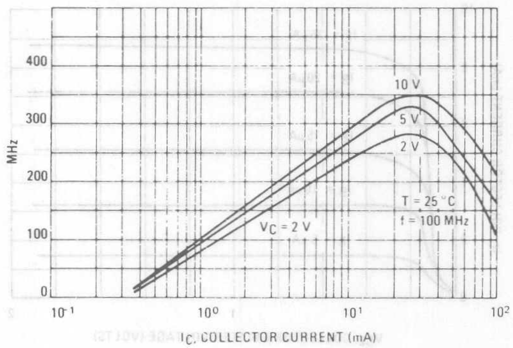
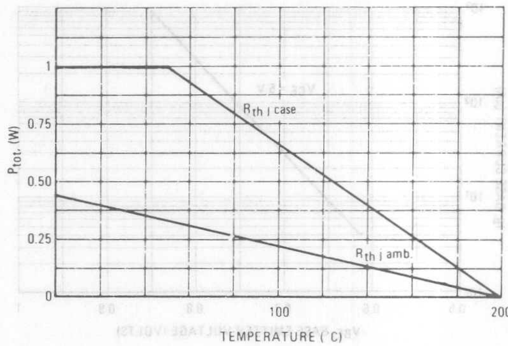
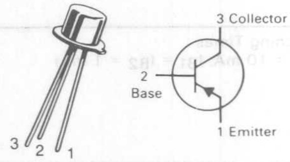


FIGURE 14 – TOTAL PERMISSIBLE POWER DISSIPATION (BCY58/BCY59)



BCY70
BCY71
BCY72

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



TRANSISTOR

PNP SILICON

Refer to 2N3798 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BCY 70	BCY 71	BCY 72	Unit
Collector-Emitter Voltage	V_{CEO}	40	45	25	Vdc
Collector-Base Voltage	V_{CBO}	50	45	25	Vdc
Emitter-Base Voltage	V_{EBO}		5		Vdc
Collector Current − Continuous	I_C		0.2		Amp
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D		360 2.06		mWatt mW/°C
Total Device Dissipation @ T_C = 25°C T_C = 100°C Derate above 25°C	P_D		0.6 4.0		mWatt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	175	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector Emitter Breakdown Voltage (I_C = 2 mA, I_B = 0)	 BCY70 BCY71 BCY72	$V_{(BR)CEO}$	 40 45 25			Vdc
Collector Base Leakage Current (I_E = 0, V_{CB} = 50 V) (I_E = 0, V_{CB} = 45 V) (I_E = 0, V_{CB} = 25 V)	 BCY70 BCY71 BCY72	I_{CBO}			 0.5 0.5 0.5	 μA
(I_E = 0, V_{CB} = 40 V, T_{Amb} = 100°C) (I_E = 0, V_{CB} = 40 V, T_{Amb} = 100°C) (I_E = 0, V_{CB} = 20 V, T_{Amb} = 100°C)	BCY70 BCY71 BCY72				2 2 2	
(I_E = 0, V_{CB} = 40 V) (I_E = 0, V_{CB} = 40 V) (I_E = 0, V_{CB} = 20 V)	BCY70 BCY71 BCY72				10 50 50	nA
Emitter Base Leakage Current (V_{EB} = 5 V, I_C = 0) (V_{EB} = 4 V, I_C = 0) (V_{EB} = 4 V, I_C = 0, T_{Amb} = 100°C)		I_{EBO}			 0.5 10 2	 μA nA μA
Collector Emitter Leakage Current (V_{CE} = 50 V, V_{BE} = 3 V)	 BCY70	I_{CEX}			 20	nA
ON CHARACTERISTICS						
DC Current Gain (V_{CE} = 1 V, I_C = 10 μA)	 BCY71	HFE	 40			
(V_{CE} = 1 V, I_C = 100 μA)	BCY70 BCY71		40 80			
(V_{CE} = 1 V, I_C = 1 mA)	BCY70 BCY71 BCY72		45 90 40			
(V_{CE} = 1 V, I_C = 10 mA)	BCY70 BCY71 BCY72		50 100 50		 600	
(V_{CE} = 1 V, I_C = 50 mA)	BCY70		15			
Base Emitter Saturation Voltage (I_C = 50 mA, I_B = 5 mA) (I_C = 10 mA, I_B = 1 mA)	 BCY70/71 BCY70/71	$V_{BE(sat)}$	 0.6		 1.2 0.9	V
Collector Emitter Saturation Voltage (I_C = 50 mA, I_B = 5 mA) (I_C = 10 mA, I_B = 1 mA)		$V_{CE(sat)}$			 0.50 0.25	V

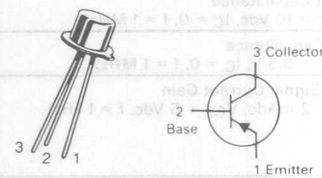
4

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS						
Transition Frequency		f_T				MHz
(I_C = 10 mA, f = 100 MHz, V_{CE} = 20 V)	All types		250			
(I_C = 100 μA, f = 10.7 MHz, V_{CE} = 20 V)	BCY71 only		15			
Noise Figure		NF				dB
(V_{CE} = 5 V, I_C = 100 μA, Rg = 2 KΩ, 30 to 15 kHz at −3 dB points)						
	BCY70/72				6	
	BCY71				2	
Switching Times						ns
(I_C = 10 mA, I_{B1} = I_{B2} = 1 mA)	BCY70/72	t_{on}			65	
	BCY70/72	t_{off}			420	
	BCY70/72	t_d			35	
	BCY70/72	t_r			35	
	BCY70/72	t_s			350	
	BCY70/72	t_f			80	
h parameters						
(V_{CE} = 10 V, I_C = 1 mA, f = 1 kHz)	BCY71	h_{12e}	—		20×10^{4}	—
		h_{21e}	100		400	—
		h_{22e}	10		60	μs
		h_{11e}	2		12	KΩ
Common Base Output Capacitance (V_{CB} = 10 V, I_E = 0, f = 1 MHz)		C_{ob}			6	pF
Input Capacitance (V_{BE} = 1 V, I_C = 0, f = 1 MHz		C_{ib}			8	pF

BCY78,-VII,VIII,IX,X
BCY79,-VII,VIII,IX,X

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	BCY 78	BCY 79	Unit
Collector-Emitter Voltage	V_{CEO}	32	45	Vdc
Collector-Emitter Voltage (R_{BE} = 10 Ohms)	V_{CES}	32	45	Vdc
Emitter-Base Voltage	V_{EBO}	5		Vdc
Collector Current − Continuous	I_C	0.2		Amp
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.6 2.28		Watt mW/°C
Total Device Dissipation @ T_C = 25°C T_C = 100°C Derate above 25°C	P_D	1 6.67		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	150	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	450	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Type	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_C = 0)	BCY78 BCY79	$V_{(BR)CEO}$	32 45			Vdc
Emitter-Base Breakdown Voltage (I_E = 2 μAdc, I_C = 0)	all	$V_{(BR)EBO}$	5			Vdc
Collector Cutoff Current (V_{CE} = 32 V) (V_{CE} = 45 V)	 BCY78 BCY79	I_{CES}		 0.2 0.2	 100 100	nA
(V_{CE} = 32 V, T_A = 100°C, V_{BE} = 0.2 V) (V_{CE} = 45 V, T_A = 100°C, V_{BE} = 0.2 V)	BCY78 BCY79	I_{CEX}			20 20	μAdc
(V_{CE} = 25 V, T_A = 150°) (V_{CE} = 35 V, T_A = 150°)	BCY78 BCY79	I_{CES}		0.2 0.5	10 10	μAdc
Emitter Base Cutoff Current (V_{EB} = 4 V)	all	I_{EBO}			20	nA
ON CHARACTERISTICS						
DC Current Gain		h_{FE}				
(I_C = 10 μAdc, V_{CE} = 5 Vdc)	BCY79-VII, BCY78-VII					
	BCY79-VIII, BCY78-VIII		30	145		
	BCY79-IX, BCY78-IX		40	220		
	BCY79-X, BCY78-X		100	300		
(I_C = 2 mAdc, V_{CE} = 5 Vdc)	BCY79-VII, BCY78-VII		120	170	220	
	BCY79-VIII, BCY78-VIII		180	250	310	
	BCY79-IX, BCY78-IX		250	350	460	
	BCY79-X, BCY78-X		380	500	630	
(I_C = 10 mAdc, V_{CE} = 1 Vdc)	BCY79-VII, BCY78-VII		80	190		
	BCY79-VIII, BCY78-VIII		120	260	400	
	BCY79-IX, BCY78-IX		160	380	630	
	BCY79-X, BCY78-X		240	550	1000	
(I_C = 100 mAdc, V_{CE} = 1 Vdc)	BCY79-VII, BCY78-VII		40			
	BCY79-VIII, BCY78-VIII		45			
	BCY79-IX, BCY78-IX		60			
	BCY79-X, BCY78-X		60			
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 2.5 mAdc) (I_C = 10 mAdc, I_B = 0.25 mA)	all	$V_{CE(sat)}$	 0.15 0.05	 0.30 0.12	 0.80 0.25	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.25 mA) (I_C = 100 mA, I_B = 2.5 mA)	all	$V_{BE(sat)}$	 0.6 0.75	 0.70 0.90	 0.85 1.2	Vdc
Base-Emitter on Voltage (I_C = 2 mAdc, V_{CE} = 5 Vdc)	all	$V_{BE(on)}$	0.60	0.62	0.75	Vdc

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Type	Symbol	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5 V, f = 100 MHz)	all	f_T	180	300		MHz
Output Capacitance (V_{CE} = 10 Vdc, I_C = 0, f = 1 MHz)	all	C_{ob}		3.5	7	pF
Input Capacitance (V_{BE} = 0.5 V, I_C = 0, f = 1 MHz)	all	C_{ib}		8	15	pF
Small Signal Current Gain (I_C = 2 mAdc, V_{CE} = 5 Vdc, f = 1 kHz)	BCY78-VII, BCY79-VII BCY78-VIII, BCY79-VIII BCY78-IX, BCY79-IX BCY78-X, BCY79-X	h_{fe} (h_{21e})		200 260 330 520		
Input Impedance (I_C = 2 mAdc, V_{CE} = 5 Vdc, f = 1 kHz)	BCY78-VII, BCY79-VII BCY78-VIII, BCY79-VIII BCY78-IX, BCY79-IX BCY78-X, BCY79-X	h_{ie} (h_{11e})	1.6 2.5 3.2 7.5		4.5 6 8.5 12	Kohms
Voltage Feedback Ratio (I_C = 2 mAdc, V_{CE} = 5 Vdc, f = 1 kHz)	BCY78-VII, BCY79-VII BCY78-VIII, BCY79-VIII BCY78-IX, BCY79-IX BCY78-X, BCY79-X	h_{re} (h_{12e})		1.5 2 2 3		$\times 10^{-4}$
Noise Figure (I_C = 0.2 mAdc, V_{CE} = 5 Vdc, R_S = 2 Kohms, f = 1 kHz)	all	N_F		2	6	dB
SWITCHING CHARACTERISTICS						
I_C = 10 mA, I_{B1} = 1 mA, I_{B2} = 1 mA V_{BB} = 3.6 V, R_1 = R_2 = 5 KΩ R_L = 990 ohms		t_d t_r t_{on}		35 50 85	 150	nS
* See test circuit.		t_s t_f t_{off}		400 80 480	 800	
I_C = 100 mA, I_{B1} = 10 mA, I_{B2} = 10 mA V_{BB} = 5 V, R_1 = 500 Ω, R_2 = 700 Ω R_L = 98 ohms		t_d t_r t_{on}		5 50 55	 150	nS
* See test circuit.		t_s t_f t_{off}		250 200 450	 800	

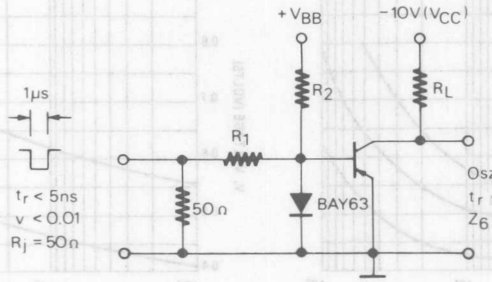


FIGURE 1 – CURRENT GAIN (BCY78-VII/BCY79-VII)

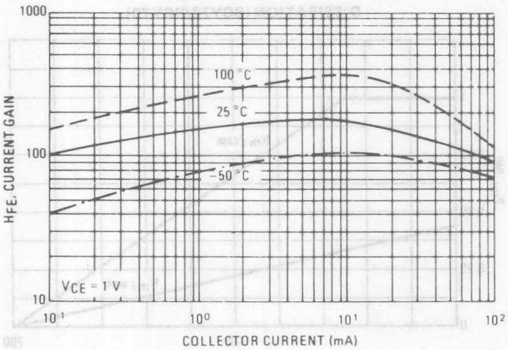


FIGURE 2 – CURRENT GAIN (BCY78-VIII/BCY79-VIII)

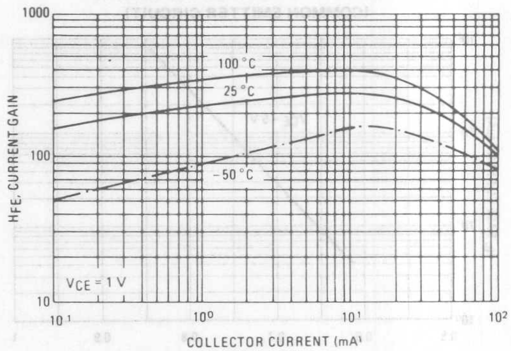


FIGURE 3 – CURRENT GAIN (BCY78-IX/BCY79-IX)

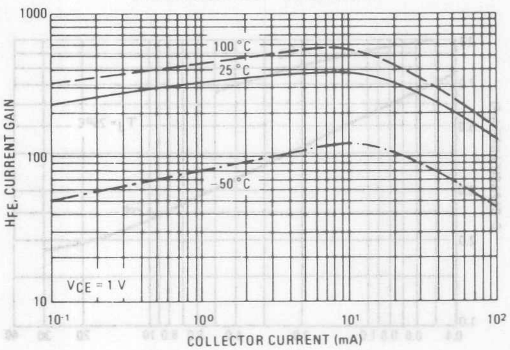
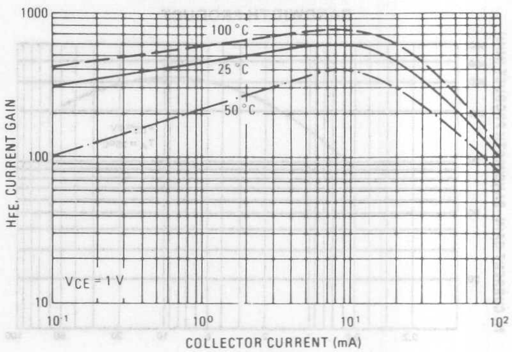


FIGURE 4 – CURRENT GAIN (BCY78-X/BCY79-X)



4

FIGURE 5 – SATURATION VOLTAGE

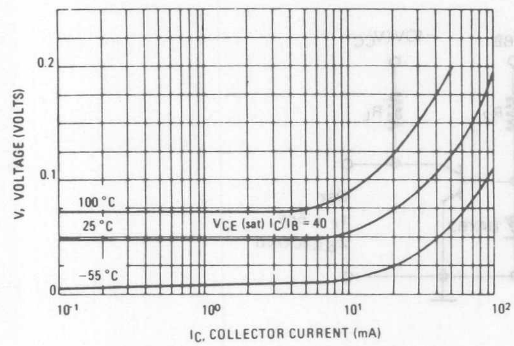


FIGURE 6 – SATURATION VOLTAGE

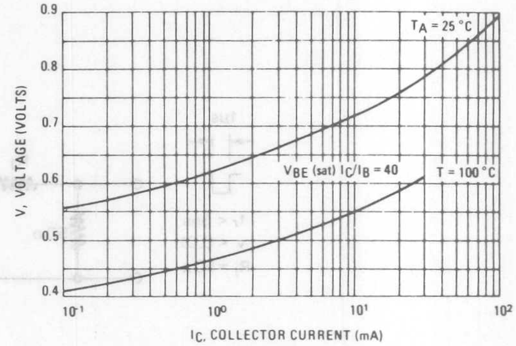


FIGURE 7 – INPUT CHARACTERISTIC (COMMON EMITTER CIRCUIT)

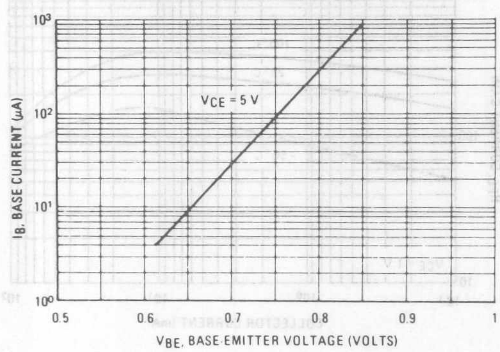


FIGURE 8 – TOTAL PERMISSIBLE POWER DISSIPATION (BCY78/BCY79)

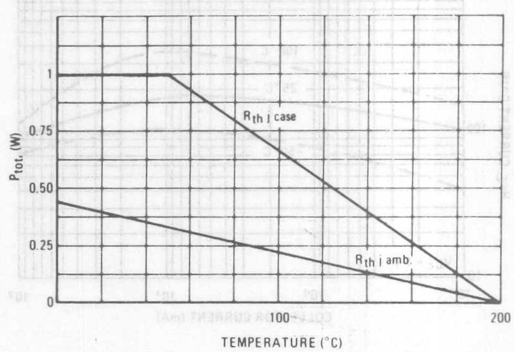


FIGURE 9 – CURRENT GAIN BANDWIDTH PRODUCT

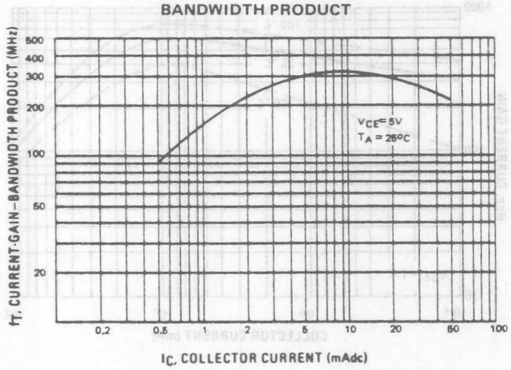
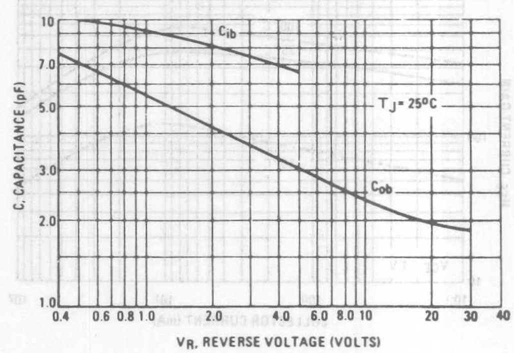
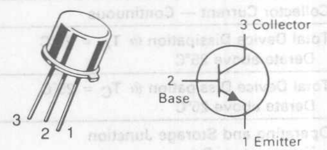


FIGURE 10 – CAPACITANCES



BF257
BF258
BF259

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



HIGH VOLTAGE TRANSISTOR

NPN SILICON

4

MAXIMUM RATINGS

Rating	Symbol	BF 257	BF 258	BF 259	Unit
Collector-Emitter Voltage	V_{CEO}	160	250	300	Vdc
Collector-Emitter Voltage	V_{CER}	160	250	300	Vdc
Collector-Base Voltage	V_{CBO}	160	250	300	Vdc
Emitter-Base Voltage	V_{EBO}	5.0			Vdc
Collector Current − Continuous	I_C	0.1			Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.8 4.57			Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	5.0 28.6			Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200			°C

THERMAL CHARACTERISTICS

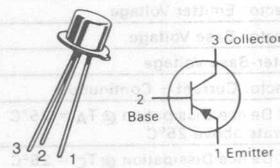
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 30 mAdc, I_B = 0)	BF257 BF258 BF259	$V_{(BR)CEO}$	160 250 300	— — —		Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	BF257 BF258 BF259	$V_{(BR)CBO}$	160 250 300	— — —		Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—		Vdc
Collector Cutoff Current (V_{CB} = 100 Vdc, I_E = 0) (V_{CB} = 200 Vdc, I_E = 0) (V_{CB} = 250 Vdc, I_E = 0)	BF257 BF258 BF259	I_{CBO}	— — —	1 1 1	50 50 50	nAdc
ON CHARACTERISTICS						
DC Current Gain (I_C = 30 mAdc, V_{CE} = 10 Vdc)		h_{FE}	25	80	—	—
Collector-Emitter Saturation Voltage (I_C = 30 mAdc, I_B = 6.0 mAdc)		$V_{CE(sat)}$	—	0.1	1.0	Vdc
DYNAMIC CHARACTERISTICS						
Current Gain Bandwidth Product (I_C = 30 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	—	110	—	MHz
Reverse Transfer Capacitance (V_{CB} = 30 Vdc, I_E = 0, f = 500 kHz)		C_{re}	—	3.5	—	pF
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 500 kHz)		C_{cb}	—	5.5	—	pF

BFW43

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



HIGH VOLTAGE TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	150	Vdc
Collector-Base Voltage	V_{CBO}	150	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	0.1	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.4 2.66	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.4 8.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

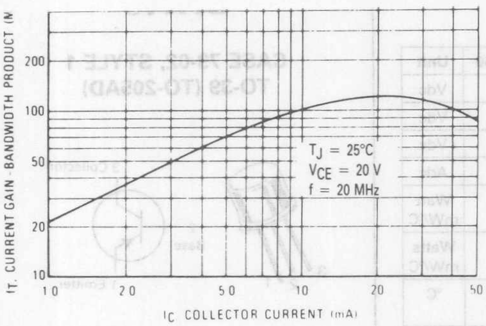
THERMAL CHARACTERISTICS

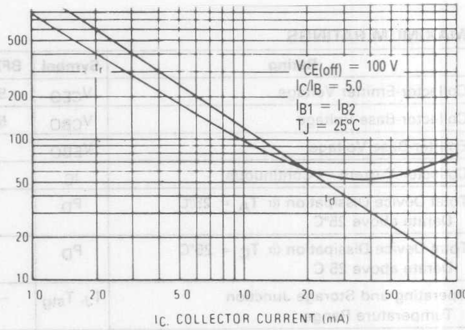
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	438	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 2$ mA, $I_B = 0$)	$V_{(BR)CEO}$	150			Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	150			Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	6			Vdc
Collector Cutoff Current ($V_{CB} = 100$ V, $I_E = 0$)	I_{CBO}			10	nA
Collector-Emitter Cutoff Current ($V_{CB} = 100$ V, $I_B = 0$) $T_A = 125°C$	I_{CEO}			10	μA
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 1$ mA, $V_{CE} = 10$ V) ($I_C = 10$ mA, $V_{CE} = 10$ V) ($I_C = 10$ μA, $V_{CE} = 10$ V, $T_A = -55°C$)	h_{FE}	 40 40 	 30		
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1$ mAdc)	$V_{CE(sat)}$		0.15	0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1$ mAdc)	$V_{BE(sat)}$		0.7	0.9	Vdc
DYNAMIC CHARACTERISTICS					
Current Gain Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 10 MHz)	f_T	60	110	200	MHz
Output Capacitance ($I_E = 0$, $V_{CB} = 20$ Vdc, f = 1 MHz)	C_{obo}	—	3.5	7	pF
Turn On Time ($I_{B1} = 10$ mA, $I_C = 50$ mAdc, $V_{CC} = 100$ Vdc)	t_{on}	—	100	—	ns
Turn Off Time ($I_{B2} = 10$ mAdc, $I_C = 50$ mAdc, $V_{CC} = 100$ Vdc)	t_{off}	—	400	—	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.





4

FIGURE 3 — TURN-OFF TIME

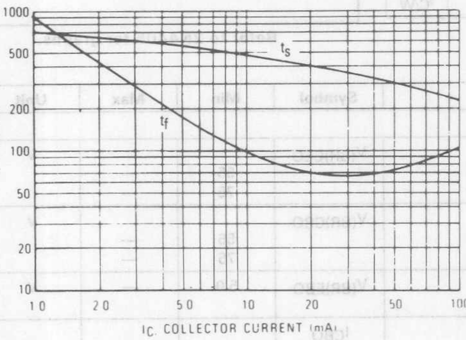
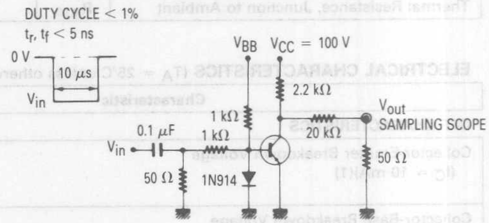


FIGURE 4 — SWITCHING TIME TEST CIRCUIT



	V_{in}	V_{BB}
t_{on}	−10.6 V	
t_{off}	−20 V	+9.2 V

4

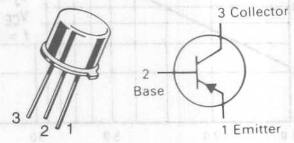
MAXIMUM RATINGS

Rating	Symbol	BFX38	BFX40	Unit
Collector-Emitter Voltage	V_{CEO}	55	75	Vdc
Collector-Base Voltage	V_{CBO}	55	75	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	1.0		Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.25 7.15		Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	7.0 40		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	20	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	140	°C/W

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



HIGH CURRENT TRANSISTOR

PNP SILICON

Refer to 2N4405 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 mA)(1)	 BFX38 BFX40	$V_{(BR)CEO}$	 55 75	 — —	V
Collector-Base Breakdown Voltage (I_C = 10 μA)	 BFX38 BFX40	$V_{(BR)CBO}$	 55 75	 — —	V
Emitter-Base Breakdown Voltage (I_E = 10 μA)		$V_{(BR)EBO}$	5.0	—	V
Collector Cutoff Current (V_{CB} = 40 V) (V_{CB} = 50 V) (V_{CB} = 40 V, T_A = 125°C) (V_{CB} = 50 V, T_A = 125°C)	 BFX38 BFX40 BFX38 BFX40	I_{CBO}	 — — — —	 50 50 50 50	 nA μA
ON CHARACTERISTICS					
Collector-Emitter Saturation Voltage (I_C = 150 mA, I_B = 15 mA)(1) (I_C = 500 mA, I_B = 50 mA)(1)		$V_{CE(sat)}$	 — —	 0.15 0.5	V
DC Current Gain (I_C = 100 μA, V_{CE} = 5.0 V)(1) (I_C = 100 mA, V_{CE} = 5.0 V)(1) (I_C = 500 mA, V_{CE} = 5.0 V)(1) (I_C = 1.0 A, V_{CE} = 5.0 V)(1)	 BFX38/40 BFX38/40 BFX38/40 BFX38 BFX40	h_{FE}	 60 85 60 30 25	 — — — — —	—
Emitter-Base Saturation Voltage (I_C = 150 mA, I_B = 15 mA)(1) (I_C = 500 mA, I_B = 50 mA)(1)		$V_{BE(sat)}$	 — —	 0.9 1.1	V
DC Current Gain (I_C = 100 mA, V_{CE} = 5.0 V, T_A = 125°C)(1)	 BFX38/40	h_{FE}	30	—	—

(1) Pulsed: Pulse Duration = 300 μs, Duty Cycle = 1.0%.

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
SMALL SIGNAL CHARACTERISTICS				
Current Gain — Bandwidth Product (I_C = 50 mA, V_{CE} = 10 V, f = 100 MHz)	f_T	100		MHz
Output Capacitance (V_{CB} = 10 V)	C_{ob}		20	pF
Input Capacitance (V_{EB} = 0.5 V)	C_{ib}		120	pF
Turn On Time (I_C = 500 mA, I_{B1} = 50 mA)	t_{on}		100	ns
Turn Off Time (I_C = 500 mA, I_{B1} = I_{B2} = 50 mA)	t_{off}		350	ns
Fall Time (I_C = 500 mA, I_{B1} = I_{B2} = 50 mA)	t_f		50	ns

4

BFX48

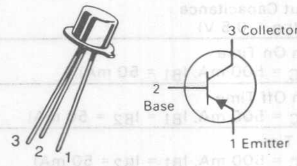
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	0.1	Amp
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.36 2.06	Watt mW/°C
Total Device Dissipation @ T_C = 25°C T_C = 100°C	P_D	1.2 0.686	Watt
Derate above 25°C		6.86	mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	146	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	486	°C/W

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

PNP SILICON

Refer to 2N869A for graphs.

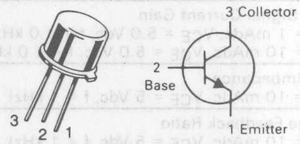
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 10 mA) (1)	$V_{(BR)CEO}$	30		V
Collector-Base Breakdown Voltage (I_C = 10 μA)	$V_{(BR)CBO}$	30		V
Emitter-Base Breakdown Voltage (I_E = 10 μA)	$V_{(BR)EBO}$	5		V
Collector Cutoff Current (V_{CE} = 20 V) (V_{CE} = 20 V, T_A = 125°C)	I_{CES}		 15 15	 nA μA
ON CHARACTERISTICS				
DC Current Gain (I_C = 10 μA, V_{CE} = 1 V) (I_C = 100 μA, V_{CE} = 1 V) (I_C = 10 mA, V_{CE} = 1 V) (I_C = 50 mA, V_{CE} = 1 V) (I_C = 10 mA, V_{CE} = 1 V, T_A = −55°C)	h_{FE}	 40 70 90 20 30		
Collector-Emitter Saturation Voltage (I_C = 1 mA, I_B = 0.1 mA) (I_C = 10 mA, I_B = 1 mA) (I_C = 50 mA, I_B = 5 mA) (1)	$V_{CE(sat)}$		 0.13 0.14 0.3	V
Emitter-Base Saturation Voltage (I_C = 1 mA, I_B = 0.1 mA) (I_C = 10 mA, I_B = 1 mA) (I_C = 50 mA, I_B = 5 mA) (1)	$V_{BE(sat)}$		 0.75 0.9 1.1	V
SMALL SIGNAL CHARACTERISTICS				
Current Gain — Bandwidth Product (I_C = 10 mA, V_{CE} = 20 V, f = 100 MHz)	f_T	400		MHz
Output Capacitance (V_{CB} = 10 V)	C_{ob}		3.5	pF
Input Capacitance (V_{EB} = 0.5 V)	C_{ib}		5.5	pF
Noise Figure (I_C = 1 mA, V_{CE} = 20 V, f = 100 MHz)	NF		6	dB
Turn On Time (I_C = 50 mA, I_{B1} = 5 mA)	t_{on}		50	ns
Turn Off Time (I_C = 50 mA, I_{B1} = I_{B2} = 5 mA)	t_{off}		160	ns
Collector-Base Time Constant (I_C = 10 mA, V_{CE} = 20 V, f = 80 MHz)	$r_b'C_c$		40	ps

(1) Pulsed: Pulse Duration = 300 μs, Duty Cycle = 1%.

BFX85

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N3019 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	60	Vdc
Collector-Base Voltage	V_{CBO}	100	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current − Continuous	I_C	1.0	Amp
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.8 4.57	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	220	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, V_{BE} = 0)	$V_{(BR)CEO}$	60		Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_B = 0)	$V_{(BR)CBO}$	100		Vdc
Collector Cutoff Current (V_{CB} = 80 Vdc, I_E = 0) (V_{CB} = 80 Vdc, I_E = 0, T_j = 100°C) (V_{CB} = 100 Vdc, I_E = 0) (V_{CB} = 100 Vdc, I_E = 0, T_j = 100°C)	I_{CBO}		 50 2.5 500 2.5	 nAdc μAdc nAdc μAdc
Emitter Cutoff Current (V_{EB} = 5 Vdc, I_C = 0) (V_{EB} = 5 Vdc, I_C = 0, T_j = 100°C) (V_{EB} = 6 Vdc, I_C = 0)	I_{EBO}		 50 2.5 500	 nAdc μAdc nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 10 mAdc, V_{CE} = 10 Vdc) (I_C = 150 mAdc, V_{CE} = 10 Vdc) (I_C = 500 mAdc, V_{CE} = 10 Vdc) (I_C = 1.0 Adc, V_{CE} = 10 Vdc)	h_{FE}	 50 70 30 15		
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc) (I_C = 1.0 Adc, I_B = 100 mAdc)	$V_{CE(sat)}$		 0.15 0.35 1.00 1.60	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc) (I_C = 1.0 Adc, I_B = 100 mAdc)	$V_{BE(sat)}$		 1.2 1.3 1.5 2.0	Vdc

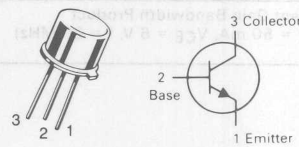
4

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
SMALL SIGNAL CHARACTERISTICS				
Current Gain Bandwidth Product (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 35 MHz)	f_T	50		MHz
Collector Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1 MHz)	C_{obo}		12	pF
Small Signal Current Gain (I_C = 1 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz) (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{fe}	 20 25		
Input Impedance (I_C = 10 mAdc, V_{CE} = 5 Vdc, f = 1 kHz)	h_{ie}		750	Ω
Voltage Feedback Ratio (I_C = 10 mAdc, V_{CE} = 5 Vdc, f = 1 kHz)	h_{re}		5.0	$\times 10^{-4}$
Output Admittance (I_C = 10 mAdc, V_{CE} = 5 Vdc, f = 1 kHz)	h_{oe}		80	μmhos

BFY50
BFY51
BFY52

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N3019 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BFY 50	BFY 51	BFY 52	Unit
Collector-Emitter Voltage	V_{CEO}	35	30	20	Vdc
Collector-Base Voltage	V_{CBO}	80	60	40	Vdc
Emitter-Base Voltage	V_{EBO}	6			Vdc
Collector Current − Continuous	I_C	1			Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.8 4.6			Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5 28.6			Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	16.5	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	89.5	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 10$ mA)	BFY50 BFY51 BFY52	$V_{(BR)CEO}$	35 30 20		V
Collector-Base Breakdown Voltage ($I_C = 10\ \mu A$)	BFY50 BFY51 BFY52	$V_{(BR)CBO}$	80 60 40		V
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu A$)		$V_{(BR)EBO}$	6		V
Collector Cutoff Current ($V_{CB} = 60$ V) ($V_{CB} = 40$ V) ($V_{CB} = 30$ V)	BFY50 BFY51 BFY52	I_{CBO}		50	nA
Collector Cutoff Current ($V_{CB} = 60$ V, $T_j = 100°C$) ($V_{CB} = 40$ V, $T_j = 100°C$) ($V_{CB} = 30$ V, $T_j = 100°C$)	BFY50 BFY51 BFY52	I_{CBO}		2.5	μA
Emitter Cutoff Current ($V_{EB} = 5$ V) ($V_{EB} = 5$ V, $T_j = 100°C$)		I_{EBO}		50 2.8	nA μA
ON CHARACTERISTICS					
DC Current Gain ($I_C = 10$ mA, $V_{CE} = 6$ V)	BFY50 BFY51-52	h_{FE}	20 30		
($I_C = 150$ mA, $V_{CE} = 6$ V)	BFY50 BFY51 BFY52		30 40 60		
($I_C = 1$ A, $V_{CE} = 6$ V)			15		
Collector-Emitter Saturation Voltage ($I_C = 150$ mA, $I_B = 15$ mA(1))	BFY50 BFY51-52	$V_{CE(sat)}$		0.2 0.35	V
($I_C = 1$ A, $I_B = 100$ mA(1))	BFY50 BFY51-52			1 1.6	
Emitter-Base Saturation Voltage ($I_C = 1$ A, $I_B = 100$ mA(1))		$V_{BE(sat)}$		2	V

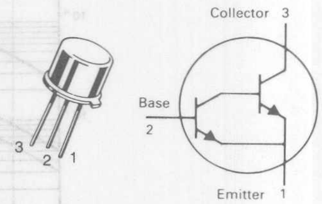
(1) Pulsed: Pulse Duration = 300 μs, Duty Cycle = 1%.

Characteristic		Symbol	Min	Max	Unit
SMALL SIGNAL CHARACTERISTICS					
Small Signal Current Gain (I_C = 1 mA, V_{CE} = 6 V, f = 1 kHz)	BFY50 BFY51-52	h_{fe}	10 30		
Output Capacitance (V_{CB} = 12 V, f = 500 kHz)		C_{ob}		12	pF
Current Gain Bandwidth Product (I_C = 50 mA, V_{CE} = 6 V, f = 20 MHz)	BFY50 BFY51-52	f_T	60 50		MHz

4

BSS50
BSS51
BSS52

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



DARLINGTON TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	BSS 50	BSS 51	BSS 52	Unit
Collector-Emitter Voltage	V_{CEO}	45	60	80	Vdc
Collector-Emitter Voltage	V_{CER}	45	60	80	Vdc
Collector-Base Voltage	V_{CBO}	60	80	100	Vdc
Emitter-Base Voltage	V_{EBO}	5.0			Vdc
Collector Current − Continuous	I_C	1.0			Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.8 5.3			Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5 28.6			Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	220	°C/W

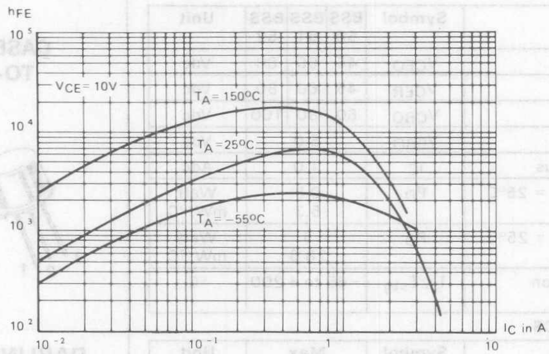
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Cutoff Current ($V_{CB} = 45$ V, $I_E = 0$) ($V_{CB} = 60$ V, $I_E = 0$) ($V_{CB} = 80$ V, $I_E = 0$)	 BSS50 BSS51 BSS52	I_{CBO}			 50 50 50	nA
Emitter-Cutoff Current ($V_{EB} = 4$ V, $I_C = 0$)		I_{EBO}			50	nA
Collector-Emitter Breakdown Voltage ($I_C = 10$ mA, $I_B = 0$)	 BSS50 BSS51 BSS52	$V_{(BR)CEO}$	 45 60 80			V
Emitter-Base Breakdown Voltage ($I_B = 100\ \mu A$, $I_C = 0$)		$V_{(BR)EBO}$	5			V
ON CHARACTERISTICS						
DC Current Gain(1) ($I_C = 150$ mA, $V_{CE} = 10$ V) ($I_C = 500$ mA, $V_{CE} = 10$ V)		h_{FE}	 1500 2000			
Base-Emitter Voltage(1) ($I_C = 150$ mA, $V_{CE} = 10$ V) ($I_C = 500$ mA, $V_{CE} = 10$ V)		$V_{BE(on)}$	 1.4 1.5		 1.55 1.65	V
Saturation Voltage(1) ($I_C = 500$ mA, $I_B = 0.5$ mA) ($I_C = 500$ mA, $I_B = 0.5$ mA) ($I_C = 1$ A, $I_B = 1$ mA) ($I_C = 1$ A, $I_B = 1$ mA) ($I_C = 1$ A, $I_B = 4$ mA) ($I_C = 1$ A, $I_B = 4$ mA)	 BSS51 BSS51 BSS50-52 BSS50-52	 $V_{CE(sat)}$ $V_{BE(sat)}$ $V_{CE(sat)}$ $V_{BE(sat)}$ $V_{CE(sat)}$ $V_{BE(sat)}$			 1.3 1.9 1.6 2.2 1.6 2.2	V
DYNAMIC CHARACTERISTICS						
Current Gain Bandwidth Product ($I_C = 500$ mA, $V_{CE} = 5$, f = 20 MHz)		f_T		70		MHz
Output Capacitance ($V_{CB} = 10$ V, $I_E = 0$, f = 1 MHz)		C_{ob}		11	25	pF
Turn On Time ($I_C = 500$ mA, $I_{B1} = -I_{B2} = 0.5$ mA) Turn Off Time ($I_C = 500$ mA, $I_{B1} = -I_{B2} = 0.5$ mA)		t_{on} t_{off}		400 1500		ns

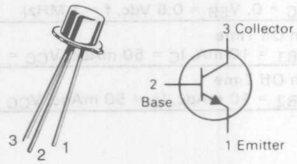
(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2%, unless otherwise specified.

4

FIGURE 1 — CURRENT GAIN versus COLLECTOR CURRENT



CASE 22-03, STYLE 1
TO-18 (TO-206AA)



HIGH VOLTAGE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	BSS 71	BSS 72	BSS 73	Unit
Collector-Emitter Voltage	V_{CEO}	200	250	300	Vdc
Collector-Base Voltage	V_{CBO}	200	250	300	Vdc
Emitter-Base Voltage	V_{EBO}	6.0			Vdc
Collector Current — Continuous	I_C	0.5			Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.5 2.86			Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 14.3			Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	70	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$				Vdc
(I_C = 10 mA, I_B = 0)	BSS71		200	—	—	
	BSS72		250	—	—	
	BSS73		300	—	—	
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$				Vdc
(I_C = 100 µAdc, I_E = 0)	BSS71		200	—	—	
	BSS72		250	—	—	
	BSS73		300	—	—	
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$				Vdc
(I_E = 100 µAdc, I_C = 0)	BSS71		6	—	—	
	BSS72		6	—	—	
	BSS73		6	—	—	
Collector Cutoff Current		I_{CBO}				nA
(V_{CB} = 150 V, I_E = 0)	BSS71				50	
(V_{CB} = 200 V, I_E = 0)	BSS72		—	—	50	
(V_{CB} = 250 V, I_E = 0)	BSS73		—	—	50	
Collector-Emitter Cutoff Current		I_{CEO}				nA
(V_{CE} = 150 V, I_B = 0)	BSS71		—	—	500	
(V_{CE} = 200 V, I_B = 0)	BSS72		—	—	500	
(V_{CE} = 300 V, I_B = 0)	BSS73		—	—	500	
Emitter-Cutoff Current		I_{EBO}				nA
(V_{BE} = 5 Vdc, I_C = 0)	ALL		—	—	50	
ON CHARACTERISTICS(1)						
DC Current Gain		h_{FE}				—
(I_C = 0.1 mA, V_{CE} = 1 V)	BSS71		20	40	—	
(I_C = 1 mA, V_{CE} = 10 V)	ALL		30	45	—	
(I_C = 10 mA, V_{CE} = 10 V)	ALL		50	120	—	
(I_C = 30 mA, V_{CE} = 10 V)	ALL		40	140	250	
(I_C = 100 mA, V_{CE} = 10 V)	BSS73		—	35	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$				Vdc
(I_C = 10 mAdc, I_B = 1 mAdc)	ALL		—	0.15	0.3	
(I_C = 30 mAdc, I_B = 3 mAdc)	ALL		—	0.25	0.4	
(I_C = 50 mAdc, I_B = 5 mAdc)	ALL		—	0.35	0.5	
(I_C = 100 mAdc, I_B = 20 mAdc)	BSS73		—	0.25	—	
Base-Emitter Saturation Voltage		$V_{BE(sat)}$				Vdc
(I_C = 10 mAdc, I_B = 1 mAdc)	ALL		—	0.7	0.8	
(I_C = 30 mAdc, I_B = 3 mAdc)	ALL		—	0.8	0.9	
(I_C = 50 mAdc, I_B = 5 mAdc)	ALL		—	0.85	1.0	
(I_C = 100 mAdc, I_B = 10 mAdc)	BSS73		—	0.9	—	

*Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2%.

Characteristic	Symbol	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS					
Current Gain Bandwidth Product (I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 20 MHz)	f_t	50	70	200	MHz
Output Capacitance (I_E = 0, V_{CB} = 20 Vdc, f = 1 MHz)	C_{ob}	—	3.5	—	pF
Input Capacitance (I_C = 0, V_{EB} = 0.5 Vdc, f = 1 MHz)	C_{ib}	—	45		pF
Turn On Time (I_{B1} = 10 mA, I_C = 50 mAdc, V_{CC} = 100 Vdc)	t_{on}	—	100		ns
Turn Off Time (I_{B2} = 10 mAdc, I_C = 50 mAdc, V_{CC} = 100 Vdc)	t_{off}	—	400	—	ns

FIGURE 1 — DC CURRENT GAIN

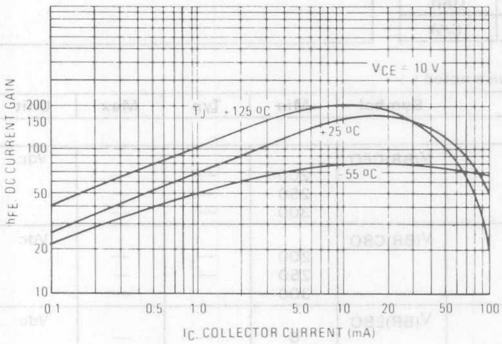


FIGURE 2 — CAPACITANCES

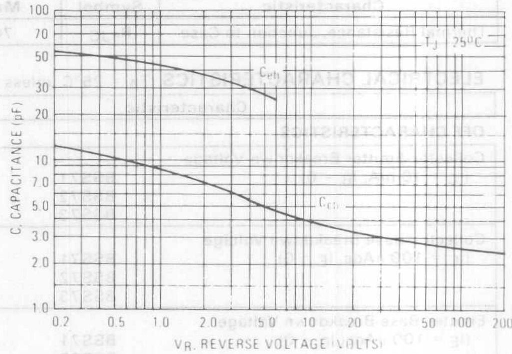


FIGURE 3 — CURRENT-GAIN — BANDWIDTH PRODUCT

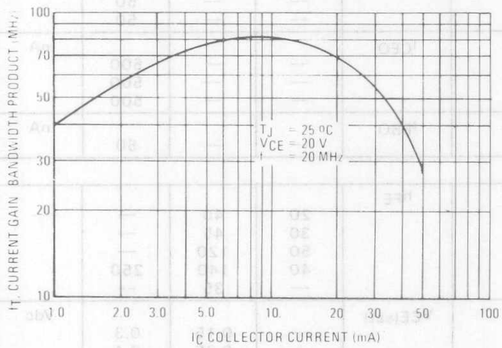


FIGURE 4 — ACTIVE-REGION SAFE OPERATING AREA

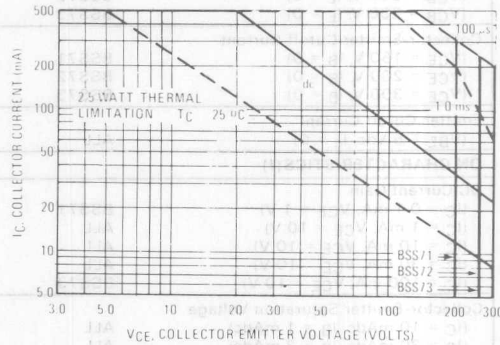


FIGURE 5 – "ON" VOLTAGES

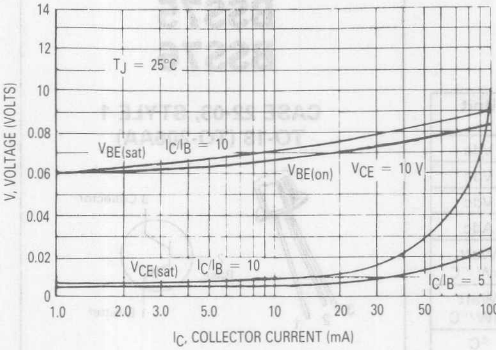


FIGURE 6 – TEMPERATURE COEFFICIENTS

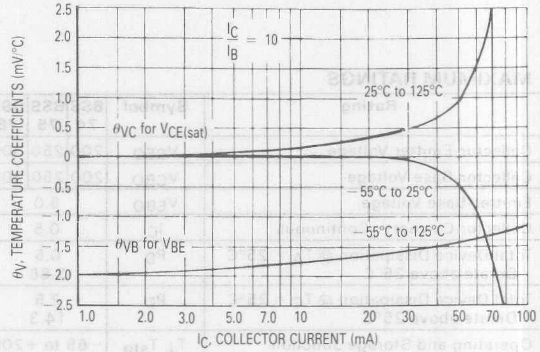


FIGURE 7 – TURN ON TIME

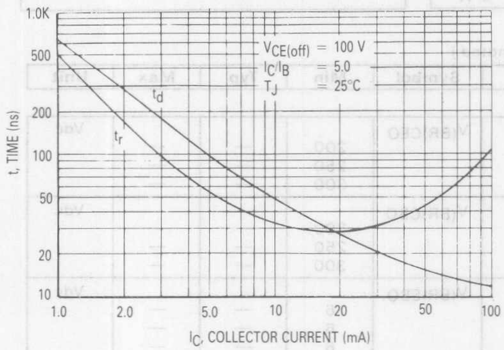


FIGURE 8 – TURN-OFF TIME

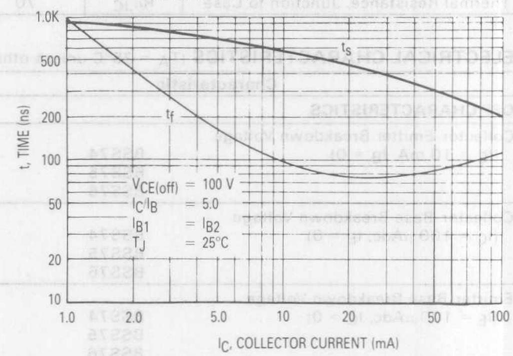
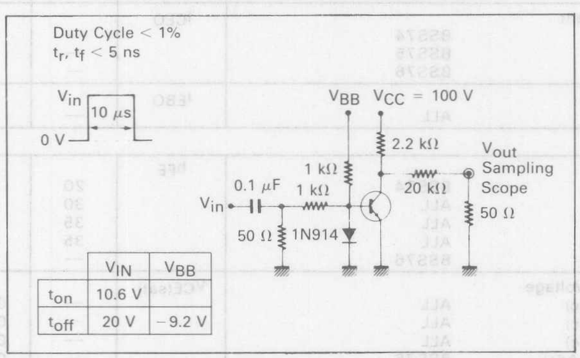


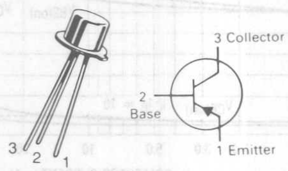
FIGURE 9 – SWITCHING TIME TEST CIRCUIT



	V_{IN}	V_{BB}
t_{on}	10.6 V	
t_{off}	20 V	−9.2 V

BSS74
BSS75
BSS76

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



HIGH VOLTAGE TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	BSS 74	BSS 75	BSS 76	Unit
Collector-Emitter Voltage	V_{CEO}	200	250	300	Vdc
Collector-Base Voltage	V_{CBO}	200	250	300	Vdc
Emitter-Base Voltage	V_{EBO}	5.0			Vdc
Collector Current — Continuous	I_C	0.5			Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.5 2.86			Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.5 14.3			Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	70	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage ($I_C = 10$ mA, $I_B = 0$)	BSS74 BSS75 BSS76	$V_{(BR)CEO}$	200 250 300	— — —	— — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	BSS74 BSS75 BSS76	$V_{(BR)CBO}$	200 250 300	— — —	— — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	BSS74 BSS75 BSS76	$V_{(BR)EBO}$	6 6 6	— — —	— — —	Vdc
Collector Cutoff Current ($V_{CB} = 150$ V, $I_E = 0$) ($V_{CB} = 200$ V, $I_E = 0$) ($V_{CB} = 250$ V, $I_E = 0$)	BSS74 BSS75 BSS76	I_{CBO}	— — —	— — —	50 50 50	nA
Collector-Emitter Cutoff Current ($V_{CE} = 150$ V, $I_B = 0$) ($V_{CE} = 200$ V, $I_B = 0$) ($V_{CE} = 300$ V, $I_B = 0$)	BSS74 BSS75 BSS76	I_{CEO}	— — —	— — —	500 500 500	nA
Emitter-Cutoff Current ($V_{BE} = 5$ Vdc, $I_C = 0$)	ALL	I_{EBO}	—	—	50	nA
ON CHARACTERISTICS(1)						
DC Current Gain ($I_C = 0.1$ mA, $V_{CE} = 1$ V) ($I_C = 1$ mA, $V_{CE} = 10$ V) ($I_C = 10$ mA, $V_{CE} = 10$ V) ($I_C = 30$ mA, $V_{CE} = 10$ V) ($I_C = 100$ mA, $V_{CE} = 10$ V)	BSS74 ALL ALL ALL BSS76	h_{FE}	20 30 35 35 —	40 45 50 55 40	— — — 150 —	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1$ mAdc) ($I_C = 30$ mAdc, $I_B = 3$ mAdc) ($I_C = 50$ mAdc, $I_B = 5$ mAdc) ($I_C = 100$ mAdc, $I_B = 20$ mAdc)	ALL ALL ALL BSS76	$V_{CE(sat)}$	— — — —	0.15 0.25 0.35 0.40	0.3 0.4 0.5 —	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1$ mAdc) ($I_C = 30$ mAdc, $I_B = 3$ mAdc) ($I_C = 50$ mAdc, $I_B = 5$ mAdc) ($I_C = 100$ mAdc, $I_B = 10$ mAdc)	ALL ALL ALL BSS76	$V_{BE(sat)}$	— — — —	0.7 0.8 0.85 0.9	0.8 0.9 1.0 —	Vdc

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS					
Current Gain Bandwidth product (I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 20 MHz)	f_t	50	110	200	MHz
Output Capacitance (I_E = 0, V_{CB} = 20 Vdc, f = 1 MHz)	C_{ob}	—	3.5	—	pF
Input Capacitance (I_C = 0, V_{EB} = 0.5 Vdc, f = 1 MHz)	C_{ib}	—	45	—	pF
Turn On Time (I_{B1} = 10 mA, I_C = 50 mAdc, V_{CC} = 100 Vdc)	t_{on}	—	100	—	ns
Turn Off Time (I_{B2} = 10 mAdc, I_C = 50 mAdc, V_{CC} = 100 Vdc)	t_{off}	—	400	—	ns

4

FIGURE 1 – DC CURRENT GAIN

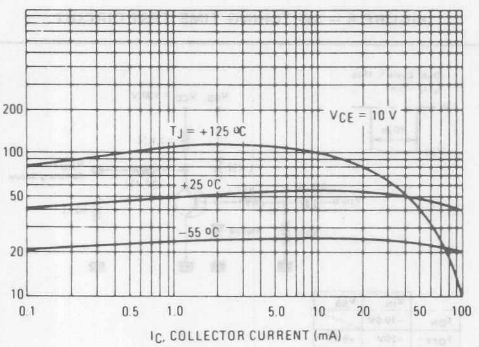


FIGURE 2 – CAPACITANCES

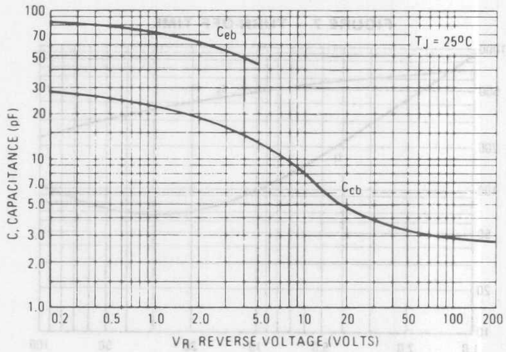


FIGURE 3 – "ON" VOLTAGES

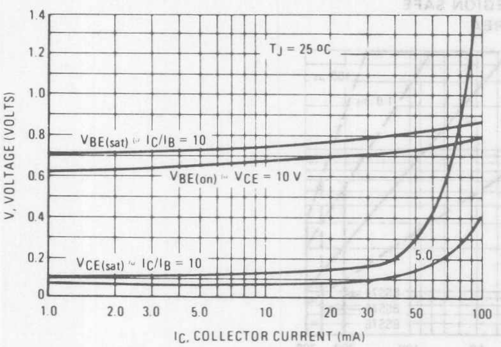
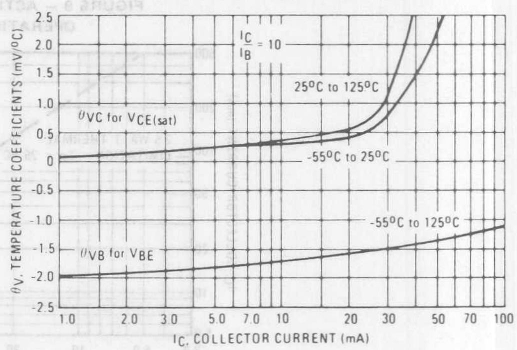
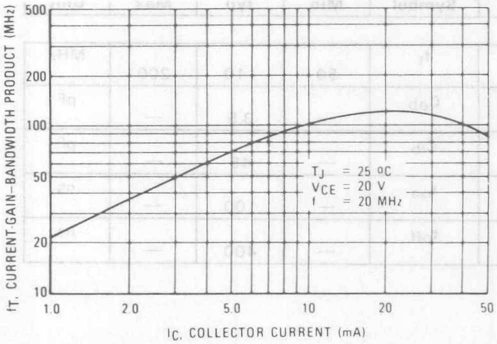


FIGURE 4 – TEMPERATURE COEFFICIENTS



4



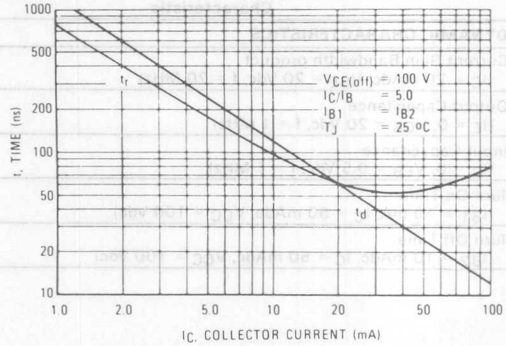


FIGURE 7 — TURN-OFF TIME

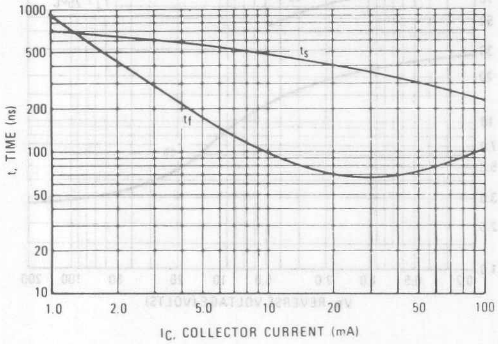


FIGURE 8 — SWITCHING TIME TEST CIRCUIT

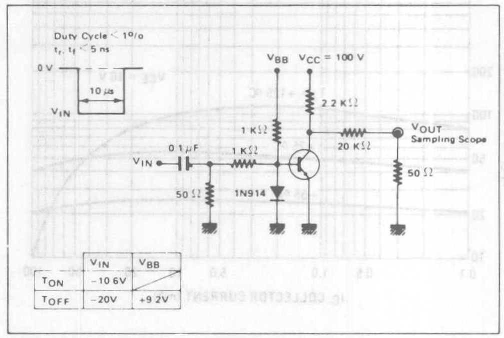
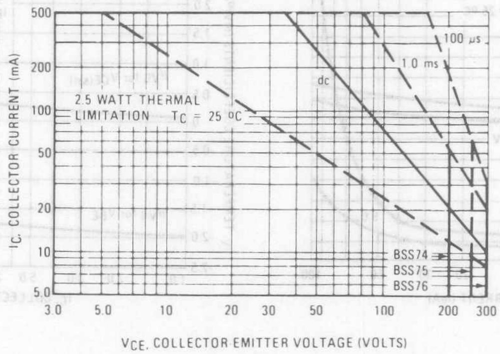
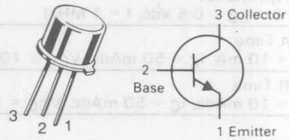


FIGURE 9 — ACTIVE-REGION SAFE OPERATING AREA



BSS78

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



HIGH VOLTAGE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	250	Vdc
Collector-Base Voltage	V_{CBO}	250	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	1.0	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.8 4.57	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5.0 28.6	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 mA, I_B = 0)	$V_{(BR)CEO}$	250	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	250	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 200 V, I_E = 0)	I_{CBO}	—	—	50	nA
Collector-Emitter Cutoff Current (V_{CE} = 200 V, I_B = 0)	I_{CEO}	—	—	500	nA
Emitter-Base Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)	I_{EBO}	—	—	50	nA
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 0.1 mA, V_{CE} = 1.0 V) (I_C = 1.0 mA, V_{CE} = 10 V) (I_C = 10 mA, V_{CE} = 10 V) (I_C = 30 mA, V_{CE} = 10 V) (I_C = 100 mA, V_{CE} = 10 V)	h_{FE}	 20 30 50 40 —	 40 45 120 140 35	 — — — 250 —	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 30 mAdc, I_B = 3.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc) (I_C = 100 mAdc, I_B = 20 mAdc)	$V_{CE(sat)}$	 — — — —	 0.15 0.25 0.35 0.25	 0.3 0.4 0.5 —	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 30 mAdc, I_B = 3.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc)	$V_{BE(sat)}$	 — — — —	 0.7 0.8 0.85 0.9	 0.8 0.9 1.0 —	Vdc

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

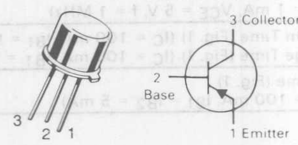
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS					
Current Gain Bandwidth Product (I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 20 MHz)	f_t	50	70	200	MHz
Output Capacitance (I_E = 0, V_{CB} = 20 Vdc, f = 1 MHz)	C_{ob}	—	3.5	—	pF
Input Capacitance (I_C = 0, V_{EB} = 0.5 Vdc, f = 1 MHz)	C_{ib}	—	45	—	pF
Turn On Time (I_{B1} = 10 mA, I_C = 50 mAdc, V_{CC} = 100 Vdc)	t_{on}	—	100	—	ns
Turn Off Time (I_{B2} = 10 mAdc, I_C = 50 mAdc, V_{CC} = 100 Vdc)	t_{off}	—	400	—	ns

4

BSV15,10,16
BSV16,10,16
BSV17,10,16

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



AMPLIFIER TRANSISTOR

PNP SILICON

Refer to 2N4405 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BSV 15	BSV 16	BSV 17	Unit
Collector-Emitter Voltage	V_{CEO}	40	60	80	Vdc
Collector-Emitter Voltage	V_{CES}	40	60	90	Vdc
Collector-Base Voltage	V_{CBO}	40	60	90	Vdc
Emitter-Base Voltage	V_{EBO}	5			Vdc
Collector Current − Continuous	I_C	1			Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.25 7.15			Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	7 40			Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	20	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	140	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

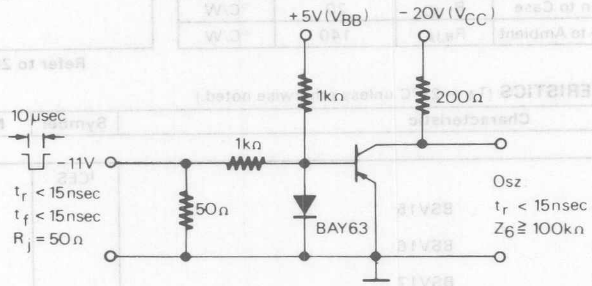
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector Cutoff Current	I_{CES}			
(V_{CE} = 40 V)			50	nA
(V_{CE} = 40 V, T_A = 150°C) BSV15			50	µA
(V_{CE} = 60 V)			50	nA
(V_{CE} = 60 V, T_A = 150°C) BSV16			50	µA
(V_{CE} = 80 V)			50	nA
(V_{CE} = 80 V, T_A = 150°C) BSV17			50	µA
(V_{CE} = 40 V, V_{BE} = −0.2 V, T_A = 100°C) BSV15	I_{CEX}		50	µA
(V_{CE} = 60 V, V_{BE} = −0.2 V, T_A = 100°C) BSV16			50	
(V_{CE} = 80 V, V_{BE} = −0.2 V, T_A = 100°C) BSV17			50	
Emitter Cutoff Current (V_{EB} = 4 V)	I_{EBO}		50	nA
Collector-Emitter Breakdown Voltage (I_C = 50 mA(1)) BSV15	$V_{(BR)CEO}$	40		V
BSV16		60		
BSV17		80		
Collector-Emitter Breakdown Voltage (I_C = 10 µA) BSV15	$V_{(BR)CES}$	40		V
BSV16		60		
BSV17		90		
Emitter-Base Breakdown Voltage (I_E = 10 µA)	$V_{(BR)EBO}$	5		V
Emitter Cutoff Current (V_{EB} = 4 V)	I_{EBO}		50	nA
ON CHARACTERISTICS				
DC Current Gain	h_{FE}			
(V_{CE} = 1 V, I_C = 0.1 mA) BSV15,16 −10		20		
BSV15,16 −16		30		
(V_{CE} = 1 V, I_C = 100 mA)(1) BSV15,16 −10		63	160	
BSV15,16 −16		100	250	
(V_{CE} = 1 V, I_C = 500 mA)(1) BSV15,16 −10		25		
BSV15,16 −16		35		
Base-Emitter Voltage	$V_{BE(on)}$			V
(V_{CE} = 1 V, I_C = 100 mA)(1)			1	
(V_{CE} = 1 V, I_C = 500 mA)(1)		0.7	1.4	

(1) Pulsed: Pulse Duration = 300 µs, Duty Cycle = 1%.

4

Characteristic	Symbol	Min	Max	Unit
SMALL SIGNAL CHARACTERISTICS				
Current Gain Bandwidth Product (I_C = 50 mA, V_{CE} = 10 V, f = 20 MHz)	f_T	50		MHz
Output Capacitance (V_{CB} = 10 V, I_E = 0, f = 1 MHz)	C_{ob}		25	pF
Small Signal Current Gain (I_C = 1 mA, V_{CE} = 5 V, f = 1 MHz)	h_{fe}	20		
Turn On Time (Fig. 1) (I_C = 100 mA, I_{B1} = I_{B2} = 5 mA)	t_{on}		500	ns
Storage Time (Fig. 1) (I_C = 100 mA, I_{B1} = I_{B2} = 5 mA)	t_s		500	
Fall Time (Fig. 1) (I_C = 100 mA, I_{B1} = I_{B2} = 5 mA)	t_f		150	ns

FIGURE 1 — SWITCHING TIME CIRCUIT

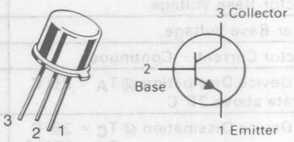


Rating	Symbol	BSW67A	BSW68A	Unit
Collector-Emitter Voltage	V_{CEO}	120	150	Vdc
Collector-Base Voltage	V_{CBO}	120	150	Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	2.0		Amp
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.8 4.57		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	5.0 28.6		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	220	°C/W

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



TRANSISTOR

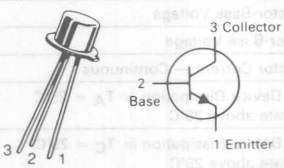
NPN SILICON

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 10$ mAdc, $I_B = 0$)	 BSW67A BSW68A	$V_{(BR)CEO}$	 120 150	 — 	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ µAdc)	 BSW67A BSW68A	$V_{(BR)CBO}$	 120 150	 — 	Vdc
Collector-Base Cutoff Current ($V_{CB} = 60$ V, $I_E = 0$) ($V_{CB} = 75$ V, $I_E = 0$) ($V_{CB} = 60$ V, $I_E = 0$, $T_J = 150°C$) ($V_{CB} = 75$ V, $I_E = 0$, $T_J = 150°C$)	 BSW67A BSW68A BSW67A BSW68A	I_{CBO}	 — — — —	 100 100 100 100	nAdc µAdc
Emitter-Base Cutoff Current ($V_{EB} = 3.0$ V, $I_C = 0$) ($V_{EB} = 6.0$ V, $I_C = 0$)		I_{EBO}	 — —	 100 100	 nAdc µAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 10$ mA, $V_{CE} = 5.0$ V) ($I_C = 100$ mA, $V_{CE} = 5.0$ V) ($I_C = 500$ mA, $V_{CE} = 5.0$ V) ($I_C = 1.0$ A, $V_{CE} = 5.0$ V)		h_{FE}	 30 40 30 15	 — — — —	
Collector-Emitter Saturation Voltage ($I_C = 100$ mA, $I_B = 10$ mA) ($I_C = 500$ mA, $I_B = 50$ mA) ($I_C = 1.0$ A, $I_B = 150$ mA)		$V_{CE(sat)}$	 — — —	 0.15 0.4 1.0	Vdc
Emitter-Base Saturation Voltage ($I_C = 100$ mA, $I_B = 10$ mA) ($I_C = 500$ mA, $I_B = 50$ mA) ($I_C = 1.0$ A, $I_B = 150$ mA)		$V_{BE(sat)}$	 — — —	 0.9 1.1 1.4	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 100$ mA, $V_{CE} = 20$ V, $f = 35$ MHz)		f_T	50	—	MHz
Output Capacitance ($V_{CB} = 10$ V, $I_E = 0$, $f = 1.0$ MHz)		C_{obo}	—	20	pF
Input Capacitance ($V_{EB} = 0$, $I_C = 0$, $f = 1.0$ MHz)		C_{ibo}	—	300	pF

BSX20

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



TRANSISTOR

NPN SILICON

4

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Emitter Voltage (R_{BE} = 10 Ohms)	V_{CER}	20	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4.5	Vdc
Collector Current – Continuous	I_C	500	mAmp
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	360 2.06	mWatt mW/°C
Total Device Dissipation @ T_C = 25°C T_C = 100°C Derate above 25°C	P_D	1.2 6.85	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	146	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0) (I_C = 10 mAdc, R_{BE} = 10 Ω)	$V_{(BR)CEO}$ $V_{(BR)CER}$	 15 20		Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	4.5		Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0) (V_{CB} = 20 Vdc, I_E = 0, T_j = 150°C)	I_{CBO}		 400 30	 nAdc μAdc
Collector Cutoff Current (V_{CE} = 15 Vdc, V_{BE} = 0, T_j = 55°C) (V_{CE} = 40 Vdc, V_{BE} = 0)	I_{CES}		 0.4 1.0	μAdc
Cutoff Current (V_{CE} = 15 Vdc, V_{BE} = −3 V, T_j = 55°C)	I_{CEX} I_{BEX}		0.6 0.6	μAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 10 mAdc, V_{CE} = 1 Vdc) (I_C = 10 mAdc, V_{CE} = 1 Vdc, T_j = −55°C) (I_C = 100 mAdc, V_{CE} = 2 Vdc)	h_{FE}	 40 20 10	 120	
Base-Emitter On Voltage (I_C = 30 μAdc, V_{CE} = 20 Vdc, T_j = 100°C)	$V_{BE(on)}$		0.35	Vdc
Emitter-Collector Saturation Voltage (I_C = 10 mAdc, I_B = 0.3 mAdc) (I_C = 10 mAdc, I_B = 1 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc)	$V_{CE(sat)}$		 0.3 0.25 0.60	Vdc
Emitter-Base Saturation Voltage (I_C = 10 mAdc, I_B = 1 mAdc) (I_C = 100 mAdc, I_B = 10 mAdc)	$V_{BE(sat)}$	 0.7	 0.85 1.50	Vdc

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
SMALL SIGNAL CHARACTERISTICS				
Current Gain Bandwidth Product (I_C = 10 mA, V_{CE} = 10 V)	f_T	500	—	MHz
Output Capacitance (V_{CB} = 5 V, I_E = 0, f = 1 MHz)	C_{obo}	—	4	pF
Input Capacitance (V_{EB} = 1 V, I_C = o, f = 1 MHz)	C_{ibo}	—	4.5	pF
Time (I_C = 10 mA, I_{B1} = I_{B2} = 10 mA)	t_s	—	13	ns
Turn-On Time (I_C = 10 mA, I_{B1} = 3 mA) (I_C = 100 mA, I_{B1} = 40 mA)	t_{on}	—	12 7	ns
Turn-Off Time (I_C = 10 mA, I_{B1} = 3 mA, I_{B2} = − 1.5 mA) (I_C = 100 mA, I_{B1} = 40 mA, I_{B2} = − 20 mA)	t_{off}	—	18 21	ns

4

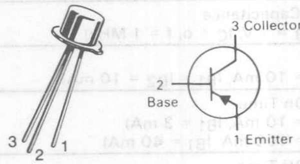
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	12	Vdc
Collector-Base Voltage	V_{CBO}	12	Vdc
Emitter-Base Voltage	V_{EBO}	5	Vdc
Collector Current – Continuous	I_C	200	Amp
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D 2.06	.36	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ $T_C = 100°C$ Derate above 25°C	P_D	1.2 0.686 6.86	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	146	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	486	°C/W

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

PNP SILICON

Refer to 2N869A for graphs.

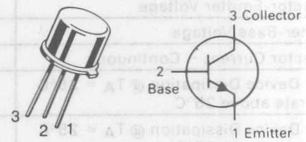
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 10$ mA)(1)	$V_{(BR)CEO}$	12		V
Collector-Emitter Breakdown Voltage ($I_C = 10\ \mu A$)	$V_{(BR)CES}$	12		V
Collector-Base Breakdown Voltage ($I_C = 10\ \mu A$)	$V_{(BR)CBO}$	12		V
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu A$)	$V_{(BR)EBO}$	4		V
Collector Cutoff Current ($V_{CE} = 6$ V, $V_{BE} = 0$) ($V_{CE} = 6$ V, $V_{BE} = 0$, $T_A = 85°C$)	I_{CES}		 80 5	 nA μA
ON CHARACTERISTICS				
Collector-Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 1$ mA) ($I_C = 30$ mA, $I_B = 3$ mA) ($I_C = 100$ mA, $I_B = 10$ mA)	$V_{CE(sat)}$		 0.15 0.2 0.5	V
Emitter-Base Saturation Voltage ($I_C = 10$ mA, $I_B = 1$ mA) ($I_C = 30$ mA, $I_B = 3$ mA) ($I_C = 100$ mA, $I_B = 10$ mA)	$V_{BE(sat)}$	 0.78 0.85	 0.98 1.2 1.7	V
DC Current Gain ($I_C = 10$ mA, $V_{CE} = 0.3$ V)(1) ($I_C = 30$ mA, $V_{CE} = 0.5$ V)(1) ($I_C = 100$ mA, $V_{CE} = 1$ V)(1)	h_{FE}	 25 30 20	 120	
Collector-Emitter Saturation Voltage ($I_C = 30$ mA, $I_B = 3$ mA, $T_A = 85°C$)	$V_{CE(sat)}$		0.4	V
SMALL SIGNAL CHARACTERISTICS				
Small Signal Current Gain ($I_C = 30$ mA, $V_{CE} = 10$ V, f = 100 MHz)	h_{fe}	4		
Output Capacitance ($V_{CB} = 5$ V)	C_{ob}		6	pF
Input Capacitance ($V_{EB} = 0.5$ V)	C_{ib}		6	pF
Turn On Time ($I_C = 30$ mA, $I_{B1} = 1.5$ mA)	t_{on}		60	ns
Turn Off Time ($I_C = 30$ mA, $I_{B1} = I_{B2} = 1.5$ mA)	t_{off}		90	ns

* Pulsed: Pulse Duration = 300 μs, Duty Cycle = 1%.

BSX32

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



SWITCHING TRANSISTOR

NPN SILICON

Refer to 2N3725 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	65	Vdc
Emitter-Base Voltage	V_{EBO}	6	Vdc
Collector Current – Continuous	I_C	1	Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.8 4.6	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	3.5 2.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

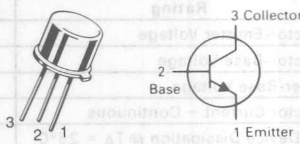
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 10 mA, I_B = 0)(1)	$V_{(BR)CEO}$	40		V
Collector-Base Breakdown Voltage (I_C = 100 μA, I_E = 0)	$V_{(BR)CBO}$	65		V
Emitter-Base Breakdown Voltage (I_E = 100 μA, I_C = 0)	$V_{(BR)EBO}$	6		V
Collector Cutoff Current (V_{CB} = 50 V, I_E = 0)	I_{CBO}		4	μA
ON CHARACTERISTICS				
DC Current Gain	h_{FE}			
(V_{CE} = 1 V, I_C = 10 mA)(1)		30		
(V_{CE} = 1 V, I_C = 100 mA)(1)		60	150	
(V_{CE} = 1 V, I_C = 500 mA)(1)		25		
(V_{CE} = 5 V, I_C = 1 A)(1)		20		
(V_{CE} = 1 V, I_C = 100 mA, T_A = −55°C)(1)		30		
(V_{CE} = 1 V, I_C = 500 mA)(1)		15		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			V
(I_C = 100 mA, I_B = 10 mA)(1)			0.25	
(I_C = 500 mA, I_B = 50 mA)(1)			0.5	
(I_C = 1 A, I_B = 100 mA)(1)			0.85	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			V
(I_C = 100 mA, I_B = 10 mA)(1)			0.9	
(I_C = 500 mA, I_B = 50 mA()(1)			1.5	
(I_C = 1 A, I_B = 100 mA)(1)			2	
SMALL SIGNAL CHARACTERISTICS				
Small Signal Current Gain (I_C = 50 mA, V_{CE} = 10 V, f = 100 MHz)	h_{fe}	3		
Output Capacitance (V_{CB} = 10 V)	C_{ob}		10	pF
Input Capacitance (V_{EB} = 0.5 V)	C_{ib}		60	pF
Turn On Time (I_C = 500 mA, I_{B1} = 50 mA)	t_{on}		60	ns
Turn Off Time (I_C = 500 mA, I_{B1} = I_{B2} = 50 mA)	t_{off}		60	ns

*Pulsed: Pulse Duration = 300 μs, Duty Cycle = 1%.

BSX45,-6,-10,-16
BSX46,-6,-10,-16
BSX47,-6,-10,-16

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N3019 for graphs.

MAXIMUM RATINGS

Rating	Symbol	BSX 45	BSX 46	BSX 47	Unit
Collector-Emitter Voltage	V_{CEO}	40	60	80	Vdc
Collector-Emitter Voltage	V_{CES}	80	100	120	Vdc
Emitter-Base Voltage	V_{EBO}		7		Vdc
Collector Current − Continuous	I_C		1		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D		1 5.71		Watt mW/°C
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D		5 28.6		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

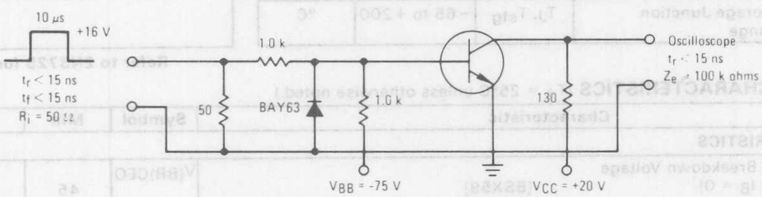
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 30 mAdc, I_B = 0)	 BSX45 BSX46 BSX47	$V_{(BR)CEO}$	 40 60 80		Vdc
Collector-Emitter Breakdown Voltage (I_C = 100 μAdc, V_{BE} = 0)	 BSX45 BSX46 BSX47	$V_{(BR)CES}$	 80 100 120		Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	7		Vdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)		I_{EBO}		10	nAdc
Collector Cutoff Current (V_{CE} = 60 V, V_{BE} = 0) (V_{CE} = 80 V, V_{BE} = 0) (V_{CE} = 60 V, V_{BE} = 0, T_C = 150°C) (V_{CE} = 80 V, V_{BE} = 0, T_C = 150°C)	 BSX45,46 BSX47 BSX45,46 BSX47	I_{CES}		 10 10 10 10	 nAdc μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc) (I_C = 100 mAdc, V_{CE} = 1.0 Vdc)(1) (I_C = 500 mAdc, V_{CE} = 1.0 Vdc)(1)	 Gr. 6 Gr. 10 Gr. 16 Gr. 6 Gr. 10 Gr. 16 Gr. 6 Gr. 10 Gr. 16	h_{FE}	 10 15 25 40 63 100 15 25 35	 100 160 250	
Base-Emitter On Voltage (I_C = 100 mAdc, V_{CE} = 1.0 Vdc) (I_C = 500 mAdc, V_{CE} = 1.0 Vdc) (I_C = 1 A, V_{CE} = 1.0 Vdc)		$V_{BE(on)}$	 0.75	 1 1.5 2	Vdc
Collector-Emitter Saturation Voltage (I_C = 1 Adc, I_B = 100 mAdc)		$V_{EC(sat)}$		1	Vdc
SMALL SIGNAL CHARACTERISTICS					
Transition Frequency (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)		f_T	50		MHz
Emitter-Base Capacitance (V_{BE} = 0.5 V, f = 1 MHz)		C_{ib}		80	pF

(1) Pulsed: Pulse Duration = 300 μs, Duty Cycle = 1%.

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

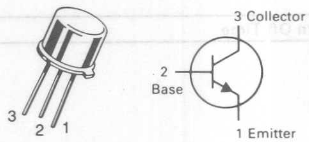
Characteristic		Symbol	Min	Max	Unit
Collector-Base Capacitance (V_{CB} = 10 V, f = 1 MHz)		C_{ob}			pF
	BSX45			25	
	BSX46			20	
	BSX47			15	
Turn On Time	See Figure 1 (I_C = 100 mAdc)	t_{on}		200	ns
Turn Off Time	I_{B1} = $-I_{B2}$ = 5 mAdc)	t_{off}		850	

FIGURE 1 – SWITCHING TIME TEST CIRCUIT



BSX60

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



SWITCHING TRANSISTOR

NPN SILICON

Refer to 2N3725 for graphs.

MAXIMUM RATINGS

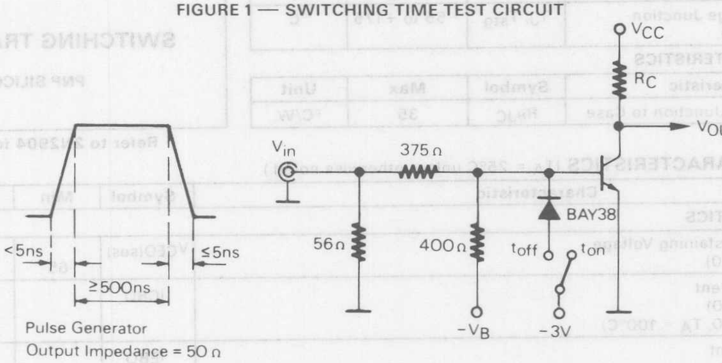
Rating	Symbol	BSX 59	BSX 60	Unit
Collector-Emitter Voltage	V_{CEO}	45	30	Vdc
Collector-Emitter Voltage	V_{CES}	60	60	Vdc
Collector-Base Voltage	V_{CBO}	70	70	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current − Continuous	I_C	1		Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.8 4.57		Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	3.5 20		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

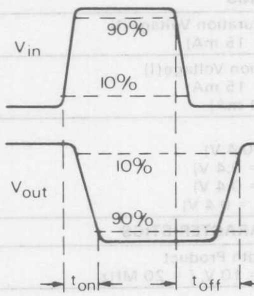
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	 [BSX59] [BSX60]	$V_{(BR)CEO}$	 45 30		V
Collector-Base Breakdown Voltage (I_C = 10 μA, I_E = 0)		$V_{(BR)CBO}$	 70		V
Collector Cutoff Current (V_{CB} = 40 V, I_E = 0) (V_{CB} = 40 V, I_E = 0, T_J = 150°C)		I_{CBO}		 500 300	 nA μA
Emitter Cutoff Current (V_{EB} = 4.0 V, I_C = 0) (V_{EB} = 4.0 V, I_E = 0, T_J = 150°C)		I_{EBO}		 300 50	 nA μA
Collector Cutoff Current (V_{CE} = 40 V, $-V_{BE}$ = 4.0 V) (V_{CE} = 40 V, $-V_{BE}$ = 4.0 V, T_J = 150°C)		I_{CEX}		 500 300	 nA μA
Emitter Cutoff Current (V_{CE} = 40 V, $-V_{BE}$ = 4.0 V) (V_{CE} = 40 V, $-V_{BE}$ = 4.0 V, T_J = 150°C)		I_{BEX}		 500 300	 nA μA
ON CHARACTERISTICS					
Collector-Emitter Saturation Voltage (I_C = 150 mA, I_B = 15 mA) (I_C = 500 mA, I_B = 50 mA) (I_C = 1.0 A, I_B = 100 mA)		$V_{CE(sat)}$		 0.3 0.5 1.0	V
Base-Emitter Saturation Voltage (I_C = 150 mA, I_B = 15 mA) (I_C = 500 mA, I_B = 50 mA) (I_C = 1.0 A, I_B = 100 mA)	 [BSX59] [BSX60]	$V_{BE(sat)}$		 1.0 1.2 1.3 1.8	V
DC Current Gain (I_C = 150 mA, V_{CE} = 1.0 V) (I_C = 500 mA, V_{CE} = 1.0 V) (I_C = 1.0 A, V_{CE} = 5.0 V)	 [BSX59] [BSX60] [BSX59] [BSX60]	h_{FE}	 30 25 30 20 25	 90	
SMALL SIGNAL CHARACTERISTICS					
Small Signal Current Gain (I_C = 50 mA, V_{CE} = 10 V, f = 100 MHz)		h_{fe}	 2.5		
Input Capacitance ($-V_{BE}$ = 0.5 V, I_C = 0, f = 1.0 MHz)		C_{ib}		 60	pF

Characteristic		Symbol	Min	Max	Unit
Output Capacitance (V_{CB} = 10 V, I_E = 0, f = 1.0 MHz)		C_{ob}		10	pF
Turn On Time (See Figure 1) (I_C = 500 mA, I_B = 50 mA, $-V_{BE}$ = 2.0 V)		t_{on}			ns
(V_{CC} = 50 V)	[BSX59]			35	
(V_{CC} = 30 V)	[BSX60]			40	
Turn Off Time (See Figure 1) (I_C = 500 mA, I_{B1} = I_{B2} = 50 mA)		T_{off}			ns
(V_{CC} = 50 V)	[BSX59]			60	
(V_{CC} = 30 V)	[BSX60]			70	

FIGURE 1 — SWITCHING TIME TEST CIRCUIT

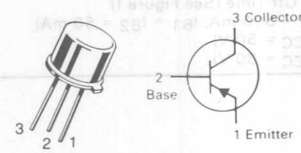


		BSX59 BSX61	BSX60	
Measure- ment	V_{CC} R_C	50 100	30 60	V Ω
t_{on}	$-V_B$ V_{in}	4.0 24.75		V V
t_{off}	$-V_B$ V_{in}	16.7 37.5		V V



CV9507

(CECC 50004-050)
CASE 79-02, STYLE 1
TO-39 (TO-205AD)



SWITCHING TRANSISTOR

PNP SILICON

Refer to 2N2904 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	65	Vdc
Collector-Base Voltage	V_{CBO}	65	Vdc
Emitter-Base Voltage	V_{EBO}	5	Vdc
Collector Current — Continuous	I_C	0.6	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.5 3.33	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +175	°C

THERMAL CHARACTERISTICS

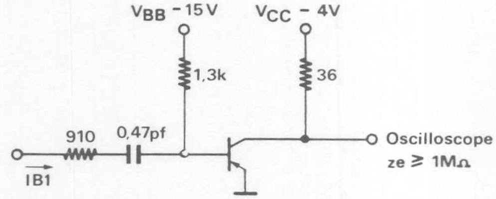
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage ($I_C = 10$ mA, $I_B = 0$)	$V_{CEO(sus)}$	65		Vdc
Collector Cutoff Current ($V_{CB} = 50$ V, $I_E = 0$) ($V_{CB} = 50$ V, $I_E = 0$, $T_A = 100°C$)	I_{CBO}		75 1	nA µA
Emitter Cutoff Current ($V_{EB} = 3$ V, $I_C = 0$) ($V_{EB} = 5$ V, $I_C = 0$)	I_{EBO}		100 10	nA µA
ON CHARACTERISTICS				
Collector-Emitter Saturation Voltage(1) ($I_C = 150$ mA, $I_B = 15$ mA)	$V_{CE(sat)}$		0.4	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 150$ mA, $I_B = 15$ mA) ($I_C = 30$ mA, $I_B = 1$ mA)	$V_{BE(sat)}$		1.3 0.9	Vdc
DC Current Gain ($I_C = 1$ mA, $V_{CE} = 0.4$ V) ($I_C = 10$ mA, $V_{CE} = 0.4$ V) ($I_C = 50$ mA, $V_{CE} = 0.4$ V) ($I_C = 150$ mA, $V_{CE} = 0.4$ V)	h_{FE}	40 50 20 10	200	
SMALL SIGNAL CHARACTERISTICS				
Current Gain Bandwidth Product ($I_C = 50$ mA, $V_{CE} = 10$ V, f = 20 MHz)	f_T	50		MHz
Output Capacitance ($V_{CB} = 10$ V, f = 1 MHz)	C_{obo}		12	pF
SWITCHING CHARACTERISTICS				
Storage Time (See Figure 1) ($V_{CC} = -4$ V, $I_C = -100$ mA) ($I_{B1} = I_{B2} = 10$ mA)	t_s		250	ns

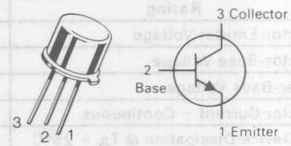
(1) Pulsed: Pulse Duration = 300 µs, Duty Cycle = 1%.

FIGURE 1 — SWITCHING TIME TEST CIRCUIT



CV10253
CV12253

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	65	Vdc
Collector-Base Voltage	V_{CBO}	65	Vdc
Emitter-Base Voltage	V_{EBO}	5	Vdc
Collector Current – Continuous	I_C	0.6	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.6 4.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +175	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	250	°C/W

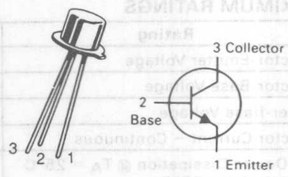
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage ($I_C = 10$ mA, $I_B = 0$)		$V_{CEO(sus)}$	65		V
Collector Cutoff Current ($V_{CB} = 50$ V, $I_E = 0$)		I_{CBO}		20	nA
Emitter Cutoff Current ($I_{EBO}(1)$ $V_{EB} = 3$ V, $I_C = 0$) ($I_{EBO}(2)$ $V_{EB} = 5$ V, $I_C = 0$)		I_{EBO}		20 2	nA µA
Collector Cutoff Current ($V_{CE} = 50$ V, $T_A = 100°C$)		I_{CEO}		80	µA
ON CHARACTERISTICS					
DC Current Gain ($h_{21e}(1)$ $I_C = 1.0$ mA, $V_{CE} = 0.4$ V) ($h_{21e}(2)$ $I_C = 10$ mA, $V_{CE} = 0.4$ V) ($h_{21e}(3)$ $I_C = 150$ mA, $V_{CE} = 0.75$ V)(1) ($h_{21e}(4)$ $I_C = 50$ mA, $V_{CE} = 0.4$ V)		h_{FE}	40 50 25 35	— 200 — —	
Base-Emitter Saturation Voltage(1) ($I_C = 30$ mA, $I_B = 1$ mA) ($I_C = 150$ mA, $I_B = 15$ mA)		$V_{BE(sat)}$		0.9 1.3	V
SMALL SIGNAL CHARACTERISTICS					
Current Gain Bandwidth Product ($I_C = 50$ mA, $V_{CE} = 10$ V, f = 35 MHz)		f_T	60		MHz
Storage Time	CV10253	t_s	172	250	ns
($V_{CC} = 45$ V, $I_C = 100$ mA, $I_{B1} = I_{B2} = 10$ mA)	CV12253			550	
Output Capacitance ($V_{CB} = 10$ V, f = 1 MHz)		C_{ob}		20	pF

(1) Pulsed: Pulse Duration = 300 µs, Duty Cycle = 1%.

4

(CECC 50004-087)
CASE 22-03, STYLE 1
TO-18 (TO-206AA)



AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	45	Vdc
Collector-Base Voltage	V_{CBO}	45	Vdc
Emitter-Base Voltage	V_{EBO}	5	Vdc
Collector Current – Continuous	I_C	250	mAmp
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.3 2.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +175	°C

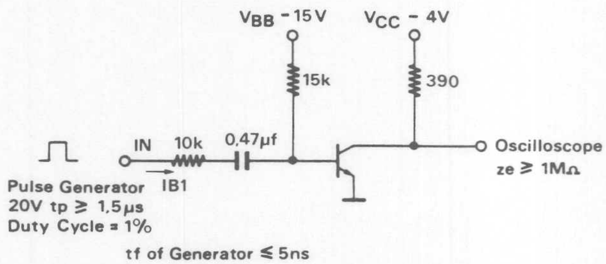
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	°C/W

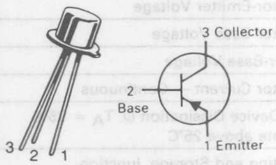
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage ($I_C = 10$ mA, $I_B = 0$)	$V_{CEO(sus)}$	45		Vdc
Collector Cutoff Current (Emitter Open) ($V_{CB} = 30$ V, $I_B = 0$) ($V_{CB} = 30$ V, $I_B = 0$, $T_A = 100°C$)	I_{CBO}		100 15	nA µA
Emitter Cutoff Current ($V_{EB} = 5$ V, $I_C = 0$)	I_{EBO}		500	nA
ON CHARACTERISTICS				
Base-Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 1$ mA) ($I_C = 50$ mA, $I_B = 2.5$ mA)	$V_{BE(sat)}$		0.9 1.6	Vdc Vdc
DC Current Gain ($I_C = 10$ µA, $V_{CE} = 0.4$ V) ($I_C = 1$ mA, $V_{CE} = 0.4$ V) ($I_C = 10$ mA, $V_{CE} = 0.4$ V)	h_{FE}	40 175 225	 500 550	
Collector-Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 1$ mA)	$V_{CE(sat)}$		0.3	Vdc
SMALL SIGNAL CHARACTERISTICS				
Current Gain Bandwidth Product ($I_C = 10$ mA, $V_{CE} = 5$ V, f = 35 MHz)	f_T	200		MHz
Output Capacitance ($V_{CB} = 5$ V, $I_E = 0$, f = 1 MHz)	C_{ob}		8	pF
SWITCHING CHARACTERISTICS				
Storage Time (See Figure 1) ($V_{CC} = 4$ V, $V_{BB} = 15$ V, $I_C = 10$ mA, $I_{B1} = I_{B2} = 1$ mA)	t_s		750	ns

FIGURE 1 – SWITCHING TIME TEST CIRCUIT



CASE 22-03, STYLE 1
TO-18 (TO-206AA)



AMPLIFIER TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	5	Vdc
Collector Current − Continuous	I_C	100	mAmp
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 2.0	mWatt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +175	°C

THERMAL CHARACTERISTICS

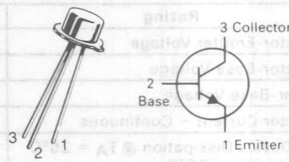
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	200	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (I_C = 2 mA, I_B = 0)	$V_{CEO(sus}$	40		V
Collector Cutoff Current (Emitter Open) (V_{CB} = 30 V, I_E = 0) (V_{CB} = 30 V, I_E = 0, T_A = 100°C)	I_{CBO}		100 4	nA μA
Emitter Cutoff Current (Collector Open) (V_{EB} = 5 V, I_C = 0)	I_{EBO}		500	nA
ON CHARACTERISTICS				
Collector-Emitter Saturation Voltage (I_C = 10 mA, I_B = 1 mA)	$V_{CE(sat)}$		0.3	V
DC Current Gain (I_C = 10 μA, V_{CE} = 5 V) (I_C = 2 mA, V_{CE} = 5 V)	h_{FE}	40 125	 400	
SMALL SIGNAL CHARACTERISTICS				
Current Gain Bandwidth Product (I_C = 10 mA, V_{CE} = 5 V, f = 100 MHz)	f_T	200		MHz
Small Signal Current Gain (I_C = 1 mA, V_{CE} = 10 V, f = 1 kHz)	h_{fe}	100	400	
Noise Figure (R_g = 2 KΩ, V_{CE} = 5 V, I_E = 200 μA, f = 30 Hz to 15 kHz	NF		2	dB
Output Capacitance (V_{CB} = 5 V, f = 1 MHz)	C_{obo}		8	pF

MM1748A

CASE 27-02, STYLE 1
TO-52 (TO-206AC)



SWITCHING TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO(sus)}$	6.0	Vdc
Collector-Base Voltage	V_{CBO}	15	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	150	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 1.71	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	583	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

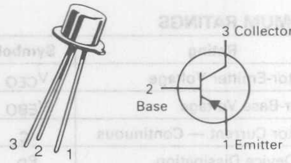
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage(2) (I_C = 10 mAdc, I_B = 0)	$V_{CEO(sus)}$	6.0	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	15	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 5.0 Vdc, I_E = 0) (V_{CB} = 5.0 Vdc, I_E = 0, T_A = 150°C)	I_{CBO}	 — —	 — —	 5.0 5.0	 nAdc μAdc
ON CHARACTERISTICS(2)					
DC Current Gain (I_C = 10 mAdc, V_{CE} = 0.5 Vdc) (I_C = 10 mAdc, V_{CE} = 0.5 Vdc, T_A = −55°C) (I_C = 30 mAdc, V_{CE} = 1.0 Vdc)	h_{FE}	 30 10 15	 55 20 20	 90 — —	—
Collector-Emitter Saturation Voltage (I_C = 3.0 mAdc, I_B = 0.15 mAdc)	$V_{CE(sat)}$	—	0.2	0.3	Vdc
Base-Emitter Saturation Voltage (I_C = 3.0 mAdc, I_B = 0.15 mAdc)	$V_{BE(sat)}$	0.7	0.78	0.85	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 5.0 mAdc, V_{CE} = 4.0 Vdc, f = 100 MHz)	f_T	800	850	—	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 140 kHz)	C_{obo}	—	2.0	3.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 140 kHz)	C_{ibo}	—	1.8	2.0	pF
SWITCHING CHARACTERISTICS					
Storage Time (V_{CC} = 3.0 Vdc, I_C = 5.0 mAdc, I_{B1} = I_{B2} = 5.0 mAdc)	t_s	—	4.0	6.0	ns
Turn-On Time (V_{CC} = 1.0 Vdc, $V_{BE(off)}$ = 1.0 Vdc, I_C = 10 mAdc, I_{B1} = 2.0 mAdc, I_{B2} = 1.0 mAdc)	t_{on}	—	12	15	ns
Turn-Off Time (V_{CC} = 1.0 Vdc, I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)	t_{off}	—	12	15	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MM2005

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



AMPLIFIER TRANSISTOR

PNP SILICON

Refer to 2N2904 for graphs.

4

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	20	Vdc
Collector-Base Voltage	V_{CBO}	25	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	600	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	400 2.28	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.4 8.0	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

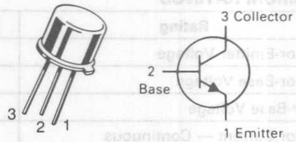
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	20	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	25	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_E = 0$)	I_{CBO}	—	—	0.5	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	100	200	400	—
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{CE(sat)}$	—	0.3	1.0	Vdc
Base-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{BE(sat)}$	—	0.7	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	6.0	15	pF
SWITCHING CHARACTERISTICS					
Turn-On Time ($V_{CC} = 30$ Vdc, $I_C = 150$ mAdc, $I_{B1} = 15$ mAdc)	t_{on}	—	20	45	μs
Turn-Off Time ($V_{CC} = 6.0$ Vdc, $I_C = 150$ mAdc, $I_{B1} = I_{B2} = 15$ mAdc)	t_{off}	—	85	100	μs

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MM3003

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

4

MAXIMUM RATINGS

Rating	Symbol	MM3001	MM3002	MM3003	Unit
Collector-Emitter Voltage	V_{CEO}	150	200	250	Vdc
Emitter-Base Voltage	V_{EBO}		5.0		Vdc
Collector Current — Continuous	I_C	200	50	50	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D		1.0 5.71		Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D		5.0 28.6		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−65 to +200		°C

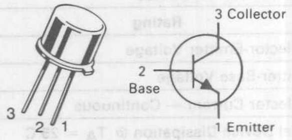
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	MM3001 MM3002 MM3003	$V_{(BR)CEO}$	150 200 150	— — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 75 Vdc, I_E = 0) (V_{CB} = 100 Vdc, I_E = 0)	MM3001 MM3002, MM3003	I_{CBO}	— —	1.0 5.0	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 10 mAdc, V_{CE} = 10 Vdc)		h_{FE}	20	—	—
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)		f_T	150	—	MHz
Output Capacitance (V_{CB} = 20 Vdc, I_E = 0, f = 100 kHz)	MM3001 MM3002, MM3003	C_{obo}	— —	7.0 15	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MM3006
MM3007

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



AUDIO TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	MM3005	MM3006	MM3007	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	100	Vdc
Collector-Base Voltage	V_{CBO}	80	100	120	Vdc
Emitter-Base Voltage	V_{EBO}		5.0		Vdc
Collector Current — Continuous	I_C		2.5		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D		1.0 5.71		Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D		8.0 45.6		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−65 to +200		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

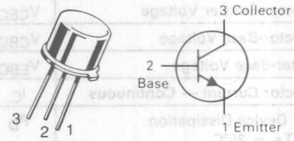
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	MM3005 MM3006 MM3007	$V_{(BR)CEO}$	60 80 100	— — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	MM3005 MM3006 MM3007	$V_{(BR)CBO}$	80 100 120	— — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 60$ Vdc, $I_E = 0$) ($V_{CB} = 80$ Vdc, $I_E = 0$) ($V_{CB} = 100$ Vdc, $I_E = 0$)	MM3005 MM3006 MM3007	I_{CBO}	— — —	100 100 100	nAdc
Emitter Cutoff Current ($V_{BE} = 4.0$ Vdc, $I_C = 0$)		I_{EBO}	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 150$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 200$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 250$ mAdc, $V_{CE} = 1.0$ Vdc)	All Types MM3005 MM3006 MM3007	h_{FE}	40 50 50 50	— 250 250 250	—
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)		$V_{CE(sat)}$	—	0.35	Vdc
Base-Emitter On Voltage ($I_C = 150$ mAdc, $V_{CE} = 1.0$ Vdc)		$V_{BE(on)}$	0.60	0.75	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(1) ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)		f_T	50	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)		C_{obo}	—	15	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

4

MM3009

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	MM3009	Unit
Collector-Emitter Voltage	V_{CEO}	180	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	400	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 5.71	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	4.0 22.8	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

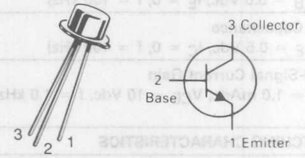
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	180		Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	6.0		Vdc
Collector Cutoff Current ($V_{CB} = 180$ Vdc, $I_E = 0$)	I_{CEO}	—	0.1	μAdc
Emitter Cutoff Current ($V_{BE} = 4.0$ Vdc, $I_C = 0$)	I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 30$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	 30 40 30	 — — —	—
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 20$ mAdc, $V_{CE} = 20$ Vdc, f = 20 MHz)	f_T	50		MHz
Output Capacitance ($V_{CB} = 20$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{obo}	—	4.0	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)	C_{ibo}	—	20	pF

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

MM3903
MM3904

CASE 27-02, STYLE 1
TO-52 (TO-206AC)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	200 2.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	500 5.0	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +125	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	490	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

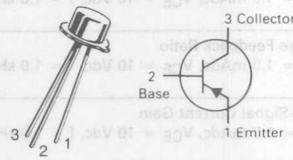
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)		$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	6.0	—	Vdc
Base Cutoff Current ($V_{CE} = 30$ Vdc, $V_{EB(off)} = 3.0$ Vdc)		I_{BEV}	—	50	nAdc
Collector Cutoff Current ($V_{CE} = 30$ Vdc, $V_{EB(off)} = 3.0$ Vdc)		I_{CEX}	—	50	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 1.0$ Vdc)	 MM3903 MM3904	h_{FE}	 20 40	 — —	—
($I_C = 1.0$ mAdc, $V_{CE} = 1.0$ Vdc)	MM3903 MM3904		35 70	— —	
($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc)	MM3903 MM3904		50 100	150 300	
($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc)	MM3903 MM3904		30 60	— —	
($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc)	MM3903 MM3904		10 15	— —	
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)		$V_{CE(sat)}$	 — —	 0.2 0.3	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)		$V_{BE(sat)}$	 0.65 —	 0.85 0.95	Vdc

SMALL-SIGNAL CHARACTERISTICS

Characteristic		Device	Symbol	Min	Max	Unit
Current-Gain — Bandwidth Product(1) (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)		MM3903 MM3904	f_T	250 300	— —	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz)			C_{obo}	—	4.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)			C_{ibo}	—	8.0	pF
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		MM3903 MM3904	h_{fe}	50 100	200 400	—
SWITCHING CHARACTERISTICS						
Delay Time	(V_{CC} = 3.0 Vdc, $V_{BE(off)}$ = 0.5 Vdc, I_C = 10 mAdc, I_{B1} = 1.0 mAdc)		t_d	—	35	ns
Rise Time			t_r	—	35	ns
Storage Time	(V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)	MM3903 MM3904	t_s	— —	175 200	ns
Fall Time			t_f	—	50	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

CASE 27-02, STYLE 1
TO-52 (TO-206AC)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

Refer to 2N3250 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	360 2.06	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	490	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)		$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Base Cutoff Current (V_{CE} = 30 Vdc, V_{BE} = 3.0 Vdc)		I_{BEV}	—	50	nAdc
Collector Cutoff Current (V_{CE} = 30 Vdc, V_{BE} = 3.0 Vdc)		I_{CEV}	—	50	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain		h_{FE}			—
(I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc)	MM3905 MM3906		30 60	— —	
(I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc)	MM3905 MM3906		40 80	— —	
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	MM3905 MM3906		50 100	150 300	
(I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	MM3905 MM3906		30 60	— —	
(I_C = 100 mAdc, V_{CE} = 1.0 Vdc)	MM3905 MM3906		10 15	— —	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{CE(sat)}$	 — —	 0.25 0.4	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{BE(sat)}$	 0.65 —	 0.85 0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(1) (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	MM3905 MM3906	f_T	200 250	— —	MHz

4

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	5.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	10	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MM3905 MM3906	h_{ie}	0.5 2.0	8.0 12	k ohms
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MM3905 MM3906	h_{re}	0.1×10^{-4} 1×10^{-4}	5×10^{-4} 10×10^{-4}	—
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MM3905 MM3906	h_{fe}	50 100	200 400	—
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	MM3905 MM3906	h_{oe}	1.0 3.0	40 60	μmhos
Noise Figure (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 k ohm, f = 10 Hz to 15.7 kHz)	MM3905 MM3906	NF	—	5.0 4.0	dB

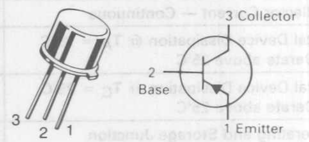
SWITCHING CHARACTERISTICS

Characteristic	Conditions		Symbol	Min	Max	Unit
Delay Time	(V_{CC} = 3.0 Vdc, $V_{BE(off)}$ = 0.5 Vdc, I_C = 10 mAdc, I_{B1} = 1.0 mAdc)		t_d	—	35	ns
Rise Time			t_r	—	35	ns
Storage Time	(V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)	MM3905 MM3906	t_s	— —	200 225	ns
Fall Time		MM3905 MM3906	t_f	— —	60 75	ns

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

MM4000 thru MM4003

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

PNP SILICON

Refer to 2N3494 for graphs for MM4000.*

MAXIMUM RATINGS

Rating	Symbol	MM4000	MM4001	MM4002	MM4003	Unit
Collector-Emitter Voltage	V_{CEO}	100	150	200	250	Vdc
Collector-Base Voltage	V_{CBO}	100	150	200	250	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	4.0	4.0	4.0	Vdc
Collector Current — Continuous	I_C	100	500	500	500	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.6 3.42	1.0 5.71	1.0 5.71	1.0 5.71	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	3.0 17.2	5.0 28.6	5.0 28.6	5.0 28.6	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−65 to +200			°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	MM4000 MM4001 MM4002 MM4003	$V_{(BR)CEO}$	100 150 200 250	— — — —	Vdc
Collector-Base Breakdown Voltage (I_E = 0, I_C = 100 μAdc)	MM4000 MM4001 MM4002 MM4003	$V_{(BR)CBO}$	100 150 200 250	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0) (V_{CB} = 75 Vdc, I_E = 0) (V_{CB} = 150 Vdc, I_E = 0)	MM4000 MM4001 MM4002, MM4003	I_{CBO}	— — —	1.0 1.0 5.0	μAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 10 mAdc, V_{CE} = 10 Vdc)		h_{FE}	20	—	—
Collector-Emitter Saturation Voltage(1) (I_C = 10 mAdc, I_B = 1.0 mAdc)	MM4000, MM4001 MM4002, MM4003	$V_{CE(sat)}$	— —	0.6 5.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance (V_{CB} = 20 Vdc, I_E = 0, f = 100 kHz)	MM4000 MM4001 MM4002, MM4003	C_{obo}	— — —	6.0 10 20	pF

(1) Pulse Test: PW ≤ 300 μs, Duty Cycle ≤ 2.0%.
*Refer to 2N3634 for graphs for MM4001.
Refer to 2N4930 for graphs for MM4002 and MM4003.

4

MAXIMUM RATINGS

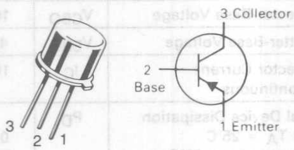
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	60	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	1.0	Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.0 5.71	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	7.0 40	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	25	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	175	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



AMPLIFIER TRANSISTOR

PNP SILICON

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	60	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0)	I_{CBO}	—	—	100	nAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_E = 0)	I_{EBO}	—	—	100	nAdc
ON CHARACTERISTICS(2)					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc) (I_C = 150 mAdc, V_{CE} = 1.0 Vdc)	h_{FE}	 40 50	 90 150	 — —	—
Collector-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{CE(sat)}$	—	0.1	—	Vdc
Base-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{BE(sat)}$	—	0.7	—	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)	f_T	50	250	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	10	—	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	—	100	—	pF

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MM4037		40	
Collector-Base Voltage MM4036 MM4037	V_{CBO}	 90 60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Base Current	I_B	500	mAdc
Collector Current — Continuous	I_C	1.0	Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 5.71	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	7.0 40	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

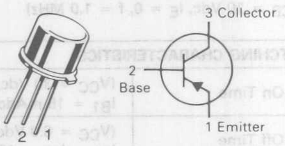
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	25	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	175	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

MM4037

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



SWITCHING TRANSISTOR

PNP SILICON

4

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	 MM4036 MM4037	$V_{(BR)CEO}$	 65 40	 —	 —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0) (I_C = 10 μAdc, I_E = 0)	 MM4036 MM4037	$V_{(BR)CBO}$	 90 60	 — —	 — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0) (I_E = 1.0 μAdc, I_C = 0)	 MM4036 MM4037	$V_{(BR)EBO}$	 5.0 5.0	 — —	 — —	Vdc
Collector Cutoff Current(1) (V_{CE} = 60 Vdc, $V_{BE(off)}$ = 1.5 Vdc) (V_{CE} = 30 Vdc, $V_{BE(off)}$ = 1.5 Vdc, T_C = 150°C)	 MM4036 MM4036	I_{CEV}	 — —	 — —	 250 100	 nAdc μAdc
Collector Cutoff Current (V_{CB} = 60 Vdc, I_E = 0)	 MM4036, MM4037	I_{CBO}	—	—	250	 nAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0) (V_{BE} = 5.0 Vdc, I_C = 0)	 MM4036 MM4037	I_{EBO}	 — —	 — —	 250 1.0	μAdc
ON CHARACTERISTICS(2)						
DC Current Gain (I_C = 100 μAdc, V_{CE} = 10 Vdc) (I_C = 150 mAdc, V_{CE} = 2.0 Vdc) (I_C = 150 mAdc, V_{CE} = 10 Vdc) (I_C = 500 mAdc, V_{CE} = 10 Vdc) (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 150 mAdc, V_{CE} = 10 Vdc)	 MM4036 MM4036 MM4036 MM4036 MM4037 MM4037	h_{FE}	 20 20 40 20 15 50	 50 60 90 40 50 75	 — 200 140 — — 250	—
Collector-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	 MM4036 MM4037	$V_{CE(sat)}$	 —	 0.3 0.3	 0.65 1.4	Vdc
Base-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)		$V_{BE(sat)}$	—	1.0	1.4	Vdc

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

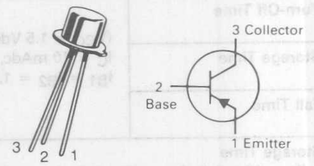
Characteristic		Symbol	Min	Typ	Max	Unit
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product(2) (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)		f_T	60	100	—	MHz
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	MM4036, MM4037	C_{ibo}	—	60		pF
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	MM4036	C_{cb}	—	20	—	pF
	MM4037		—	20	30	
SWITCHING CHARACTERISTICS						
Turn-On Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_{on}	—	40	75	ns
Turn-Off Time	(V_{CC} = 6.0 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_{off}	—	110	175	ns

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

4

MM4257
MM4258

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



SWITCHING TRANSISTOR

PNP SILICON

4

MAXIMUM RATINGS

Rating	Symbol	MM4257	MM4258	Unit
Collector-Emitter Voltage	V_{CEO}	6.0	12	Vdc
Collector-Base Voltage	V_{CBO}	6.0	12	Vdc
Emitter-Base Voltage	V_{EBO}	4.5		Vdc
Collector Current — Continuous	I_C	200		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	360 2.06		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.2 6.86		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(1) ($I_C = 100\ \mu Adc$, $V_{BE} = 0$)	MM4257 MM4258	$V_{(BR)CES}$	6.0 12	— —	— —	Vdc
Collector-Emitter Sustaining Voltage(1) ($I_C = 3.0$ mAdc, $I_B = 0$)	MM4257 MM4258	$V_{CEO(sus)}$	6.0 12	— —	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu Adc$, $I_E = 0$)	MM4257 MM4258	$V_{(BR)CBO}$	6.0 12	— —	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu Adc$, $I_C = 0$)		$V_{(BR)EBO}$	4.5	—	—	Vdc
Collector Cutoff Current ($V_{CE} = 6.0$ Vdc, $V_{BE} = 0$) ($V_{CE} = 3.0$ Vdc, $V_{BE} = 0$, $T_A = +65°C$)		I_{CES}	— —	— —	0.01 5.0	μAdc
ON CHARACTERISTICS(1)						
DC Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 0.5$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 0.3$ Vdc) ($I_C = 50$ mAdc, $V_{CE} = 1.0$ Vdc)		h_{FE}	15 30 30	— — —	— 120 —	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)		$V_{CE(sat)}$	— —	— —	0.15 0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)		$V_{BE(sat)}$	0.75 —	— —	0.95 1.5	Vdc
SMALL SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product(2) ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc, f = 100 MHz) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	MM4257 MM4258	f_T	500 700	— —	— —	MHz
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz)		C_{ibo}	—	—	3.5	pF
Collector-Base Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 100 kHz)		C_{cb}	—	—	3.0	pF

Characteristic			Symbol	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS							
Turn-On Time	(V_{CC} = 1.5 Vdc, V_{BE} = 0, I_C = 10 mAdc, I_{B1} = 1.0 mAdc)		t_{on}	—	10	15	ns
Delay Time			t_d	—	5.0	10	ns
Rise Time			t_r	—	5.0	15	ns
Turn-Off Time	(V_{CC} = 1.5 Vdc, I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)	MM4257 MM4258	t_{off}	— —	12 16	15 20	ns
Storage Time		MM4257 MM4258	t_s	— —	6.0 8.0	15 20	ns
Fall Time		MM4257 MM4258	t_f	—	6.0 8.0	10 10	ns
Storage Time (I_C ≈ 10 mAdc, I_{B1} ≈ 10 mAdc, I_{B2} ≈ 10 mAdc)		MM4257 MM4258	t_s	— —	— —	15 20	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

TYPICAL TRANSIENT CHARACTERISTICS

FIGURE 1 – CURRENT-GAIN – BANDWIDTH PRODUCT

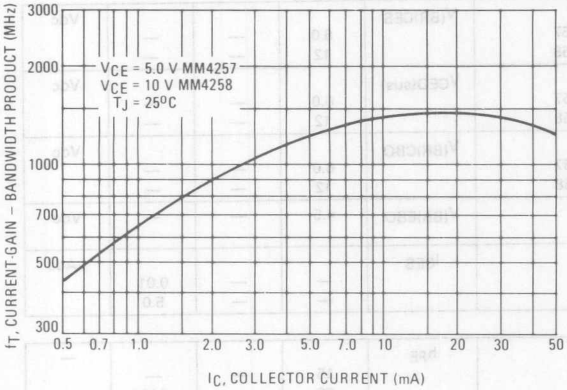


FIGURE 2 – CAPACITANCE

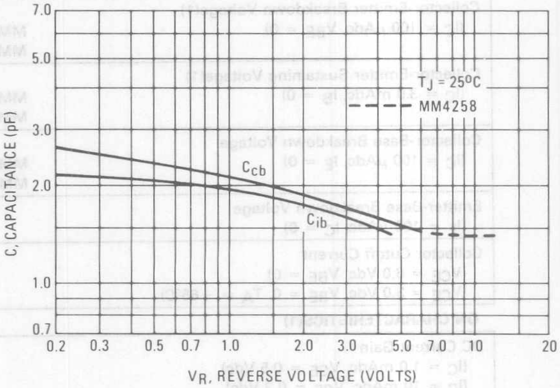


FIGURE 3 – TURN-ON TIME

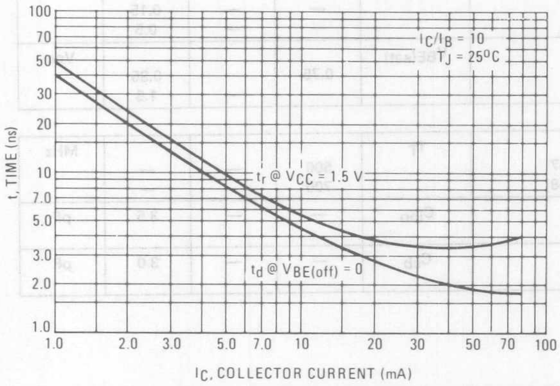


FIGURE 4 – TURN-OFF TIME

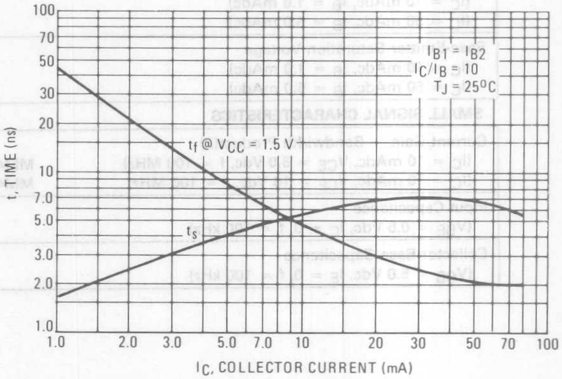
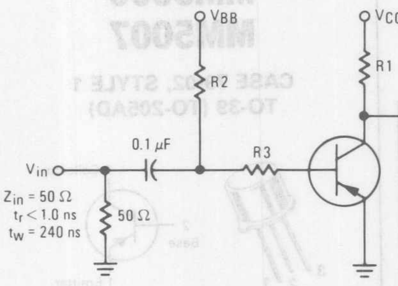


FIGURE 5 – SWITCHING TIME TEST CIRCUIT



	V_{in} Volts	V_{BB} Volts	V_{CC} Volts	R1 Ohms	R2 Ohms	R3 Ohms	I_C mA	I_{B1} mA	I_{B2} mA
t_{on}	-5.8	GND	-1.5	130	2.2 k	5 k	10	1.0	–
t_{off}	+9.8	-8.0	-1.5	130	2.2 k	5 k	10	1.0	1.0
t_s	+9.0	-10	-3.0	270	510	390	10	10	10

DC CURRENT GAIN

FIGURE 6 – MM4257

FIGURE 7 – MM4258

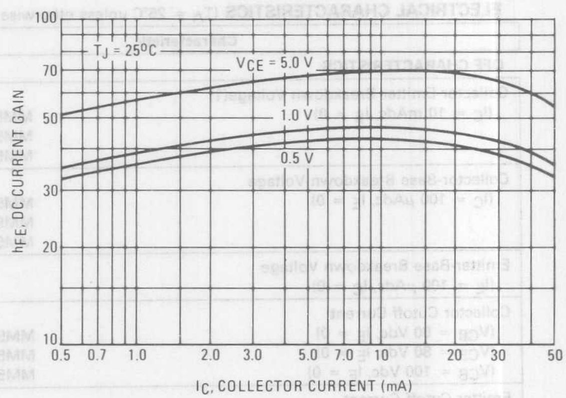
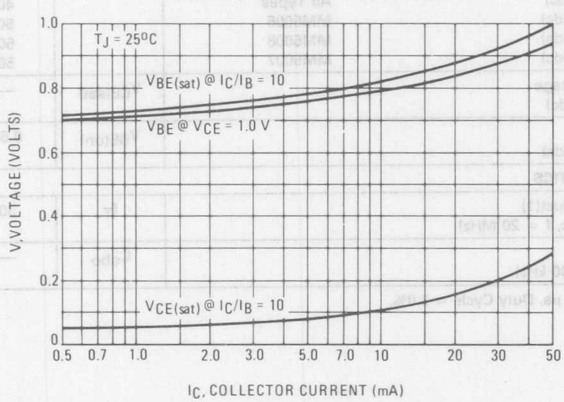


FIGURE 8 – "ON" VOLTAGES

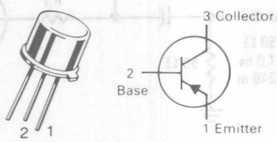


4

4

MM5005
MM5006
MM5007

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



AUDIO TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	MM5005	MM5006	MM5007	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	100	Vdc
Collector-Base Voltage	V_{CBO}	80	100	120	Vdc
Emitter-Base Voltage	V_{EBO}		5.0		Vdc
Collector Current — Continuous	I_C		2.0		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D		1.5 8.57		Watts mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D		8.0 45.7		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−65 to +200		°C

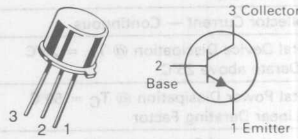
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	 MM5005 MM5006 MM5007	$V_{(BR)CEO}$	 60 80 100	 — — —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	 MM5005 MM5006 MM5007	$V_{(BR)CBO}$	 80 100 120	 — — —	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 60 Vdc, I_E = 0) (V_{CB} = 80 Vdc, I_E = 0) (V_{CB} = 100 Vdc, I_E = 0)	 MM5005 MM5006 MM5007	I_{CBO}	 — — —	 200 200 200	nAdc
Emitter Cutoff Current (V_{EB} = 4.0 Vdc, I_C = 0)		I_{EBO}	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc) (I_C = 150 mAdc, V_{CE} = 2.5 Vdc) (I_C = 200 mAdc, V_{CE} = 2.5 Vdc) (I_C = 250 mAdc, V_{CE} = 2.5 Vdc)	 All Types MM5005 MM5006 MM5007	h_{FE}	 40 50 50 50	 — 250 250 250	—
Collector-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)		$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter On Voltage (I_C = 150 mAdc, V_{CE} = 2.5 Vdc)		$V_{BE(on)}$	0.65	0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(1) (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)		f_T	30	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	20	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MM5262

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to 2N3724 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector-Emitter Voltage	V_{CES}	60	Vdc
Collector-Base Voltage	V_{CBO}	75	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	2.0	Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.0 5.71	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	4.0 22.8	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	44	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	175	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	50	—	—	Vdc
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, V_{BE} = 0)	$V_{(BR)CES}$	60	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	75	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 75 Vdc, I_E = 0)	I_{CBO}	—	—	100	μAdc
Collector Cutoff Current (V_{CE} = 60 Vdc, V_{BE} = 0)	I_{CES}	—	—	10	μAdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)	I_{EBO}	—	—	100	μAdc
ON CHARACTERISTICS(2)					
DC Current Gain (I_C = 100 mAdc, V_{CE} = 1.0 Vdc) (I_C = 500 mAdc, V_{CE} = 1.0 Vdc) (I_C = 1.0 Adc, V_{CE} = 1.0 Vdc)	h_{FE}	 35 40 25	 100 65 35	 — — —	—
Collector-Emitter Saturation Voltage (I_C = 1.0 Adc, I_B = 100 mAdc)	$V_{CE(sat)}$	—	0.29	0.8	Vdc
Base-Emitter Saturation Voltage (I_C = 1.0 Adc, I_B = 100 mAdc)	$V_{BE(sat)}$	—	0.94	1.4	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	—	350	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	7.3	—	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	—	72	—	pF
SWITCHING CHARACTERISTICS					
Turn-On Time	t_{on}	—	16	30	ns
Turn-Off Time	t_{off}	—	28	60	ns

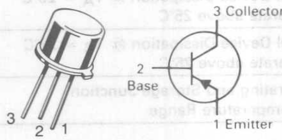
(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

4

4

MM5416

CASE 79-02, STYLE 1
TO-39 (TO-205AD)



TRANSISTOR

PNP SILICON

Refer to 2N5415 for graphs.

Rating	Symbol	MM5415	MM5416	Unit
Collector-Emitter Voltage	V_{CEO}	200	300	Vdc
Collector-Base Voltage	V_{CBO}	200	350	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	7.0	Vdc
Base Current	I_B	0.5		Adc
Collector Current — Continuous	I_C	1.0		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 6.7		Watt W/°C
Total Power Dissipation @ $T_C = 50°C$ Linear Derating Factor	P_D	10 0.057		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

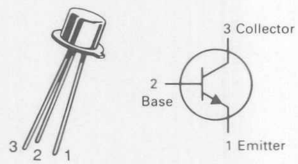
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	17.5	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	150	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage (I_C = 10 mA, I_B = 0)	MM5415 MM5416	$V_{CEO(sus)}$	200 300	— —	Vdc
Collector Cutoff Current (V_{CE} = 150 Vdc, I_B = 0)	MM5415, MM5416	I_{CEO}	—	50	μAdc
Collector Cutoff Current (V_{CE} = 175 Vdc, I_E = 0) (V_{CE} = 280 Vdc, I_E = 0)	MM5415 MM5416	I_{CBO}	— —	50 50	μAdc μAdc
Emitter Cutoff Current (V_{BE} = 4.0 Vdc, I_C = 0) (V_{BE} = 7.0 Vdc, I_C = 0)	MM5415 MM5416	I_{EBO}	— —	20 20	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 50 mAdc, V_{CE} = 10 Vdc)	MM5415 MM5416	h_{FE}	30 30	150 120	—
Collector-Emitter Saturation Voltage (I_C = 50 mAdc, I_B = 5.0 mAdc)	MM5415, MM5416	$V_{CE(sat)}$	—	2.5	Vdc
Base-Emitter On Voltage (I_C = 50 mAdc, V_{CE} = 10 V)	MM5415, MM5416	$V_{BE(on)}$	—	1.5	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 5.0 MHz)		f_T	15	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, f = 1.0 MHz)		C_{obo}	—	25	pF
Current Gain — High Frequency (I_C = 5.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		$\|h_{fe}\|$	25	—	—
Real Part of Input Impedance (I_C = 5.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 MHz)		$Re(h_{ie})$	—	300	Ohms

MM6427

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



DARLINGTON TRANSISTOR

NPN SILICON

4

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	50	Vdc
Emitter-Base Voltage	V_{EBO}	12	Vdc
Collector Current — Continuous	I_C	300	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	375 2.14	mW W/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.25 7.15	Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

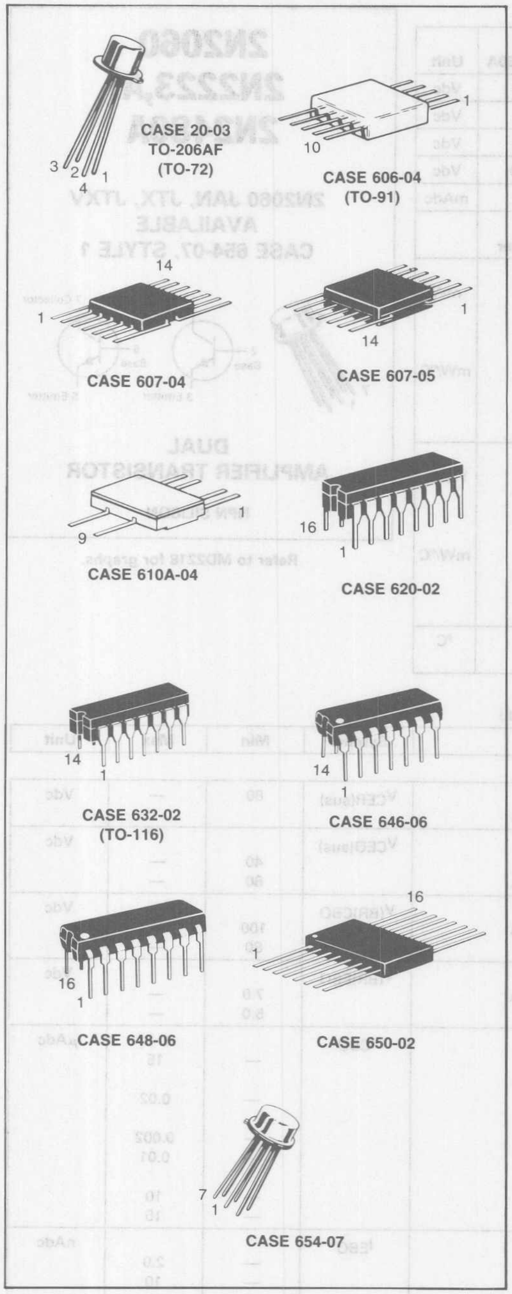
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	140	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	467	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	50	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	12	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	100	nAdc
Emitter Cutoff Current ($V_{BE} = 10$ Vdc, $I_C = 0$)	I_{EBO}	—	100	nAdc
ON CHARACTERISTICS(1)				
DC Current Gain ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 5.0$ Vdc)	h_{FE}	 5000 10,000	 — —	—
Collector-Emitter Saturation Voltage ($I_C = 100$ mAdc, $I_B = 0.1$ mAdc)	$V_{CE(sat)}$	—	1.5	Vdc
Base-Emitter On Voltage ($I_C = 100$ mAdc, $V_{CE} = 5.0$ Vdc)	$V_{BE(on)}$	—	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	8.0	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz)	C_{ibo}	—	15	pF
Small-Signal Current Gain(1) ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc, f = 100 MHz)	h_{fe}	1.25	—	—

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.



Motorola's multiple (Duals and Quads) transistors have been implemented with discrete transistor chips that have proven to be the most popular for all-around performance at low cost.

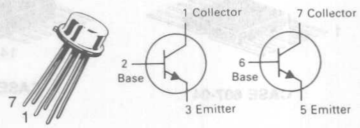
Packaging options include plastic and ceramic DIP's, ceramic flat pak, and various metal-can outlines.

Collector-Emitter Voltage	V_{CER}	80	—	—	Vdc
Collector-Base Voltage	V_{CBO}	100	75	80	Vdc
Emitter-Base Voltage	V_{EBO}	7.0	5.0	5.0	Vdc
Collector Current — Continuous	I_C	500			mAdc
		One Die	**All Die Equal Power**		
Total Device Dissipation @ $T_A = 25°C$	P_D				mW
2N2060,A		0.5	0.6		
2N2223,A		0.5	0.6		
2N2480,A		0.3	0.6		
Derate above 25°C					mW/°C
2N2060,A		2.86	3.43		
2N2223,A		2.86	3.43		
2N2480,A		1.72	3.43		
Total Device Dissipation @ $T_C = 25°C$	P_D				Watts
2N2060,A		1.5	3.0		
2N2223,A		1.6	3.0		
2N2480,A		1.0	2.0		
Derate above 25°C					mW/°C
2N2060,A		8.6	17.2		
2N2223,A		9.1	11.4		
2N2480,A		5.7	11.4		
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200			°C

2N2480A

2N2060 JAN, JTX, JTXV AVAILABLE

CASE 654-07, STYLE 1



DUAL AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MD2218 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 100 mAdc, $R_{BE} \leq$ 10 ohms)	2N2060, 2N2223, 2N2223A	$V_{CER(sus)}$	80	—	Vdc
Collector-Emitter Sustaining Voltage(1)		$V_{CEO(sus)}$			Vdc
(I_C = 20 mAdc, I_B = 0)	2N2480A		40	—	
(I_C = 30 mAdc, I_B = 0)	2N2060, 2N2223, 2N2223A		60	—	
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	2N2060, 2N2223, 2N2223A	$V_{(BR)CBO}$	100	—	Vdc
	2N2480A*		80	—	
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	2N2060, 2N2223, 2N2223A	$V_{(BR)EBO}$	7.0	—	Vdc
	2N2480A		5.0	—	
Collector Cutoff Current		I_{CBO}			μAdc
(V_{CB} = 30 Vdc, I_E = 0, T_A = 150°C)	2N2480A		—	15	
(V_{CB} = 60 Vdc, I_E = 0)	2N2480A		—	0.02	
(V_{CB} = 80 Vdc, I_E = 0)	2N2060		—	0.002	
	2N2223, 2N2223A		—	0.01	
(V_{CB} = 80 Vdc, I_E = 0, T_A = 150°C)	2N2060		—	10	
	2N2223, 2N2223A		—	15	
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)	2N2060	I_{EBO}	—	2.0	nAdc
	2N2223, 2N2223A		—	10	
	2N2480A		—	20	

Characteristic		Symbol	Min	Max	Unit
ON CHARACTERISTICS					
DC Current Gain		h_{FE}			—
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc)	2N2060		25	75	
	2N2223, 2N2223A		15	—	
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	2N2060		30	90	
	2N2223, 2N2223A		25	150	
	2N2480A		35	—	
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	2N2060		40	120	
	2N2480A		50	200	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	2N2060		50	150	
	2N2223, 2N2223A		50	200	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$			Vdc
(I_C = 50 mAdc, I_B = 5.0 mAdc)	2N2060A		—	0.6	
	2N2060, 2N2223, 2N2223A, 2N2480A		—	1.2	
Base-Emitter Saturation Voltage (I_C = 50 mAdc, I_B = 5.0 mAdc)	2N2060, 2N2223, 2N2223A, 2N2480A	$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product		f_T			MHz
(I_C = 50 mAdc, V_{CE} = 10 Vdc,	2N2223, 2N2223A, 2N2480A		50	—	
f = 20 MHz)	2N2060		60		
Output Capacitance		C_{obo}			pF
(V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	2N2060, 2N2060A, 2N2223, 2N2223A		—	15	
	2N2480A		—	18	
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	2N2060, 2N2223A, 2N2480A	C_{ibo}	—	85	pF
Input Impedance		h_{ie}			ohms
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc,	2N2060		1000	4000	
f = 1.0 kHz)	2N2480A		1000	5000	
Input Impedance		h_{ib}			ohms
(I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc,	2N2060, 2N2223, 2N2223A		20	30	
f = 1.0 kHz)	2N2480A		20	35	
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)	2N2223, 2N2223A	h_{rb}	—	3.0	$X 10^{-4}$
Small-Signal Current Gain		h_{fe}			—
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc,	2N2060		50	150	
f = 1.0 kHz)	2N2223, 2N2223A		40	200	
	2N2480A		50	300	
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	2N2060, 2N2480A	h_{oe}	—	16	μmhos
Output Admittance (I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)	2N2223, 2N2223A	h_{ob}	—	0.5	μmhos

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Noise Figure (I_C = 0.3 mAdc, V_{CE} = 10 Vdc, R_S = 510 Ω, f = 1.0 kHz, BW = 1.0 Hz)	2N2480A	NF	—	8.0	dB
(I_C = 0.3 mAdc, V_{CE} = 10 Vdc, R_S = 510 Ω, f = 1.0 kHz, BW = 200 Hz)	2N2060		—	8.0	
(I_C = 0.3 mAdc, V_{CE} = 10 Vdc, R_S = 1.0 kΩ, f = 1.0 kHz, BW = 15.7 kHz)(2)			—	8.0	
MATCHING CHARACTERISTICS					
DC Current Gain Ratio(3) (I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	2N2060, 2N2223A 2N2223, 2N2480A	h_{FE1}/h_{FE2}	0.9 0.8	1.0 1.0	—
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	2N2060 2N2480		0.9 0.8	1.0 1.0	
Base-Emitter Voltage Differential (I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	2N2060, 2N2223A, 2N2480A 2N2223	$\lvert V_{BE1}-V_{BE2} \rvert$	— —	5.0 15	mVdc
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	2N2060, 2N2060A, 2N2480A 2N2480		— —	5.0 10	
Base-Emitter Voltage Differential Change Due to Temperature (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, T_A = −55°C to +125°C)	2N2060 2N2223, 2N2223A 2N2480A	$\frac{\Delta(V_{BE1}-V_{BE2})}{\Delta T}$	— — —	10 25 15	μV/°C

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) Amplifier: 3.0 dB points at 25 Hz and 10 kHz with a roll-off of 6.9 dB per octave.
(3) The lowest h_{FE} reading is taken as h_{FE1} for this ratio.

FIGURE 1 — DC CURRENT GAIN versus COLLECTOR CURRENT

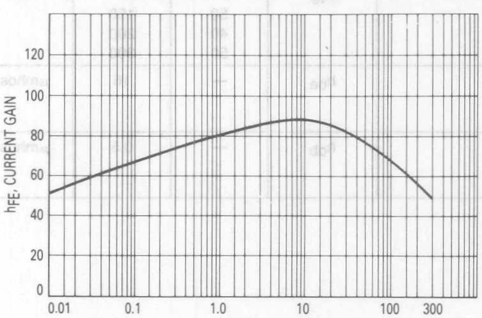
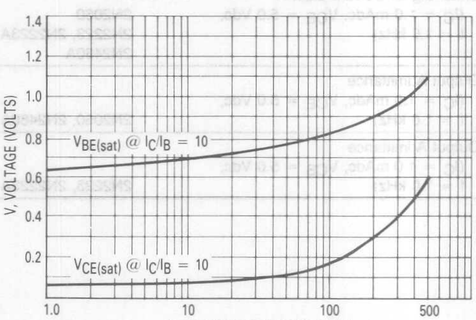
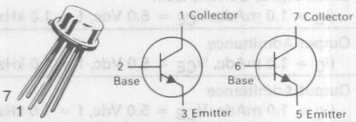


FIGURE 2 — "ON" VOLTAGES



2N2453,A

CASE 654-07, STYLE 1



DUAL
AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N2920 for graphs.

5

MAXIMUM RATINGS

Rating	Symbol	2N2453	2N2453A	Unit
Collector-Emitter Voltage	V_{CEO}	30	50	Vdc
Collector-Base Voltage	V_{CBO}	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	7.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
		One Die	**Both Die**	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	200 1.14	300 1.71	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	600 3.43	1200 6.86	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

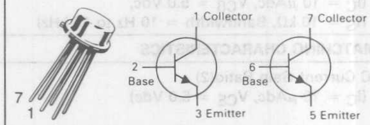
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	 2N2453 2N2453A	$V_{CEO(sus)}$	 30 50	 — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	 2N2453 2N2453A	$V_{(BR)CBO}$	 60 80	 — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 0.1\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	7.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$) ($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = 150°C$)		I_{CBO}	 — —	 0.005 10	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$)		I_{EBO}	—	0.002	μAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 10\ \mu$Adc, $V_{CE} = 5.0$ Vdc) ($I_C = 10\ \mu$Adc, $V_{CE} = 5.0$ Vdc, $T_A = -55°C$) ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, $T_A = -55°C$)		h_{FE}	 80 40 150 75	 — — 600 —	—
Collector-Emitter Saturation Voltage ($I_C = 5.0$ mAdc, $I_B = 0.5$ mAdc)		$V_{CE(sat)}$	—	1.0	Vdc
Base-Emitter Saturation Voltage ($I_C = 5.0$ mAdc, $I_B = 0.5$ mAdc)		$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 30 MHz)		f_T	60	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 140 kHz)		C_{obo}	—	8.0	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 140 kHz)		C_{ibo}	—	10	pF
Input Impedance ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz)		h_{ie}	5.0	—	kohms
Input Impedance ($I_C = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz)		h_{ib}	20	30	Ohms

Characteristic	Symbol	Min	Max	Unit
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{re}	—	6.0	X 10^{-4}
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)	h_{rb}	—	5.0	X 10^{-4}
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{fe}	150	600	—
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{oe}	5.0	30	μmhos
Output Admittance (I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)	h_{ob}	—	0.2	μmho
Noise Figure (I_C = 10 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 kΩ, f = 1.0 kHz)	NF	—	7.0	dB
MATCHING CHARACTERISTICS				
DC Current Gain Ratio(2) (I_C = 100 μAdc, V_{CE} = 5.0 Vdc) 2N2453A (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc) (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, T_A = −55°C to +125°C)	h_{FE1}/h_{FE2}	 0.90 0.90 0.85	 1.0 1.0 1.0	—
Base-Emitter Voltage Differential (I_C = 10 μAdc, V_{CE} = 5.0 Vdc) (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	$\|V_{BE1}-V_{BE2}\|$	 — —	 3.0 5.0	mVdc
Base-Emitter Voltage Differential Gradient (I_C = 10 μAdc, V_{CE} = 5.0 Vdc, T_A = −55°C to +125°C) 2N2453 2N2453A	$\frac{\Delta(V_{BE1}-V_{BE2})}{\Delta T_A}$	 — —	 10 5.0	μV/°C

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) Lowest h_{FE} reading is taken as h_{FE1} for this ratio.

thru
2N2644

CASE 654-07, STYLE 1



DUAL AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N2913 for graphs.

5

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	45		Vdc
Collector-Base Voltage	V_{CBO}	45		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	30		mAdc
		One Die	**Both Die**	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	300 1.72	600 3.43	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	600 3.43	1200 6.87	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage(1) (I_C = 10 mAdc, I_B = 0)		$V_{CEO(sus)}$	45	—	Vdc
Collector Cutoff Current (V_{CE} = 5.0 Vdc, I_B = 0)		I_{CEO}	—	0.010	μAdc
Collector Cutoff Current (V_{CB} = 45 Vdc, I_E = 0) (V_{CB} = 45 Vdc, I_E = 0, T_A = +150°C)		I_{CBO}	 — —	 0.010 10	μAdc
Emitter Cutoff Current (V_{EB} = 5.0 Vdc, I_C = 0)		I_{EBO}	—	0.010	μAdc
ON CHARACTERISTICS(1)					
DC Current Gain		h_{FE}			—
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc)	2N2639, 2N2640, 2N2641 2N2642, 2N2643, 2N2644		50 100	300 300	
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc, T_A = −55°C)	2N2639, 2N2640, 2N2641 2N2642, 2N2643, 2N2644		10 20	— —	
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	2N2639, 2N2640, 2N2641 2N2642, 2N2643, 2N2644		55 110	— —	
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	2N2639, 2N2640, 2N2641 2N2642, 2N2643, 2N2644		65 130	— —	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.5 mAdc)		$V_{CE(sat)}$	—	1.0	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.5 mAdc)		$V_{BE(sat)}$	0.6	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 20 MHz)		f_T	40	—	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	8.0	pF
Input Impedance (I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz, I_E = −1.0 mA)		h_{ib}	25	32	ohms
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz, I_E = −1.0 mA)		h_{rb}	—	600	$X\ 10^{-6}$

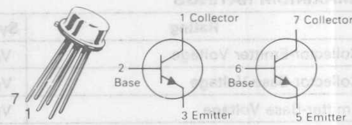
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)	2N2639, 2N2640, 2N2641 2N2642, 2N2643, 2N2644	h_{fe}	65 130	600 600	—
Output Admittance (I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz, I_E = −1.0 mA)		h_{ob}	—	1.0	μmhos
Noise Figure (I_C = 10 μAdc, V_{CB} = 5.0 Vdc, R_S = 10 kΩ, Bandwidth = 10 Hz to 15 kHz)		NF	—	4.0	dB
MATCHING CHARACTERISTICS					
DC Current Gain Ratio(2) (I_C = 10 μAdc, V_{CE} = 5.0 Vdc)	2N2639, 2N2642 2N2640, 2N2643	h_{FE1}/h_{FE2}	0.9 0.8	1.0 1.0	—
Base-Emitter Voltage Differential (I_C = 10 μAdc, V_{CE} = 5.0 Vdc)	2N2639, 2N2642 2N2640, 2N2643	$\|V_{BE1}-V_{BE2}\|$	— —	5.0 10	mVdc
Base-Emitter Voltage Differential Gradient (I_C = 10 μAdc, V_{CE} = 5.0 Vdc, T_A = −55 to +125°C)	2N2639, 2N2642 2N2640, 2N2643	$\frac{\Delta(V_{BE1}-V_{BE2})}{\Delta T_A}$	— —	10 20	μV/°C

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) The lowest h_{FE} reading is taken as h_{FE1} for this test.

2N2652,A

CASE 654-07, STYLE 1



DUAL AMPLIFIER TRANSISTOR

NPN SILICON

5

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	60		Vdc
Collector-Base Voltage	V_{CBO}	100		Vdc
Emitter-Base Voltage	V_{EBO}	7.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
		One Die	Both Die	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.3 1.72	0.6 3.43	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.0 5.7	2.0 11.4	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

Refer to 2N2060,A for graphs.

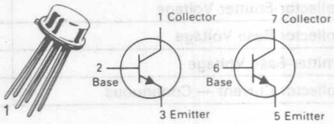
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 20$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	60	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100$ μAdc, $I_E = 0$)		$V_{(BR)CBO}$	100	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	7.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$) ($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = 150°C$)		I_{CBO}	—	0.010 15	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$)	2N2652	I_{EBO}	—	0.010	μAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 100$ μAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, $T_A = -55°C$)		h_{FE}	35 50 15	— 200 —	—
Collector-Emitter Saturation Voltage ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)		$V_{CE(sat)}$	—	1.2	Vdc
Base-Emitter Saturation Voltage ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)		$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)		f_T	60	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{obo}	—	15	pF
Input Capacitance ($V_{BE} = 0, 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)		C_{ibo}	—	85	pF
Input Impedance ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz)		h_{ie}	1.0	10.5	kohms
Input Impedance ($I_C = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz)		h_{ib}	20	35	ohms
Small-Signal Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz)		h_{fe}	50	300	—
Output Admittance ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz)		h_{oe}	—	50	μmhos
Noise Figure ($I_C = 0.3$ mAdc, $V_{CE} = 10$ Vdc, $R_S = 610$ ohms, B. W. = 1.0 Hz, f = 1.0 kHz)		NF	—	8.0	dB
MATCHING CHARACTERISTICS					
DC Current Gain Ratio(2) ($I_C = 100$ μAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc)	2N2652 2N2652	h_{FE1}/h_{FE2}	0.85 0.85	1.0 1.0	—
Base-Emitter Voltage Differential ($I_C = 100$ μAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc)		$\|V_{BE1}-V_{BE2}\|$	—	3.0 3.0	mVdc
Base-Emitter Voltage Differential Gradient ($I_C = 100$ μAdc, $V_{CE} = 5.0$ Vdc, $T_A = -55$ to $+125°C$)		$\frac{\Delta(V_{BE1}-V_{BE2})}{\Delta T_A}$	—	10	μV/°C

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) The lowest of the two h_{FE} readings is taken as h_{FE1} for the purpose of measurement.

[redacted]

CASE 654-07, STYLE 1



DUAL AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	60		Vdc
Collector-Base Voltage	V_{CBO}	80		Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	40		mAdc
		One Die	Both Die	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.3 1.71	0.6 3.4	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	0.6 3.4	1.2 6.8	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

Refer to 2N2060 for graphs.

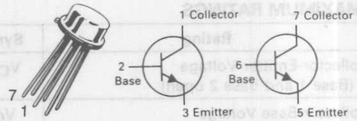
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	60	—	Vdc
Collector Cutoff Current ($V_{CE} = 5.0$ Vdc, $I_B = 0$)	I_{CEO}	—	10	nAdc
Collector Cutoff Current ($V_{CB} = 60$ Vdc, $I_E = 0$) ($V_{CB} = 60$ Vdc, $I_E = 0$, $T_A = 150°C$)	I_{CBO}	— —	0.01 10	µAdc
Emitter Cutoff Current ($V_{EB} = 5.0$ Vdc, $I_C = 0$)	I_{EBO}	—	10	nAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 100$ µAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc)	h_{FE}	30 35 42	120 —	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	1.0	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	0.65	0.85	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)	f_T	80	—	MHz
Output Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{obo}	—	6.0	pF
Input Impedance ($I_E = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz)	h_{ib}	25	32	ohms
Voltage Feedback Ratio ($I_E = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz)	h_{rb}	—	500	$\times 10^{-6}$
Small-Signal Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz)	h_{fe}	30	200	—
Output Admittance ($I_E = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz)	h_{ob}	—	1.0	µmhos
MATCHING CHARACTERISTICS				
DC Current Gain Ratio(2) ($I_C = 100$ µAdc, $V_{CE} = 5.0$ Vdc)	h_{FE1}/h_{FE2}	0.8	1.0	—
Base-Emitter Voltage Differential ($I_C = 100$ µAdc, $V_{CE} = 5.0$ Vdc)	$\vert V_{BE1}-V_{BE2}\vert$	—	10	mVdc
Base-Emitter Voltage Differential Change Due to Temperature ($I_C = 100$ µAdc, $V_{CE} = 5.0$ Vdc, $T_A = -55$ to $+25°C$) ($I_C = 100$ µAdc, $V_{CE} = 5.0$ Vdc, $T_A = +25$ to $+125°C$)	$\Delta(V_{BE1}-V_{BE2})$	— —	1.6 2.0	mV

(1) Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.
(2) The lower of the two h_{FE} readings is taken as h_{FE1} for the purpose of measurement.

2N2722

CASE 654-07, STYLE 1



DUAL AMPLIFIER TRANSISTOR

NPN SILICON

5

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	45		Vdc
Collector-Base Voltage	V_{CBO}	45		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	40		mAdc
		One Die	Both Die	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.3 1.7	0.6 3.4	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	0.6 3.4	1.2 6.8	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

Refer to 2N2920 for graphs.

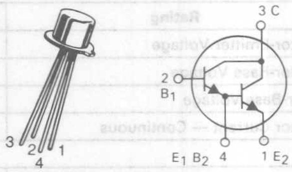
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	45	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	45	—	Vdc
Collector Cutoff Current (V_{CE} = 5.0 Vdc, I_B = 0)	I_{CEO}		2.0	nAdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0) (V_{CB} = 30 Vdc, I_E = 0, T_A = 150°C)	I_{CBO}	— —	0.001 1.0	μAdc
Emitter Cutoff Current (V_{EB} = 5.0 Vdc, I_C = 0)	I_{EBO}	—	1.0	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 1.0 μAdc, V_{CE} = 5.0 Vdc) (I_C = 10 μAdc, V_{CE} = 5.0 Vdc) (I_C = 0.1 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}	50 100 125	250 — 	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.5 mAdc)	$V_{CE(sat)}$	—	1.0	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.5 mAdc)	$V_{BE(sat)}$	0.65	0.85	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)	f_T	100	—	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	6.0	pF
Input Impedance (I_E = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)	h_{ib}	25	32	ohms
Voltage Feedback Ratio (I_E = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)	h_{rb}		600	$X\ 10^{-6}$
Small-Signal Current Gain (I_E = 0.1 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	h_{fe}	100	700	—
Output Admittance (I_E = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)	h_{ob}	—	1.0	μmhos
Noise Figure (I_C = 10 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 kΩ, f = 10 Hz to 15.7 kHz)	NF	—	4.0	dB
MATCHING CHARACTERISTICS				
DC Current Gain Ratio(2) (I_C = 1.0 μAdc, V_{CE} = 5.0 Vdc)	h_{FE1}/h_{FE2}	0.9	1.0	—
Base-Emitter Voltage Differential (I_C = 10 μAdc, V_{CE} = 5.0 Vdc)	$\lvert V_{BE1}-V_{BE2}\rvert$	—	5.0	mVdc
Base-Emitter Voltage Differential Change Due to Temperature (I_C = 10 μAdc, V_{CE} = 5.0 Vdc, T_A = −55 to +25°C) (I_C = 10 μAdc, V_{CE} = 5.0 Vdc, T_A = +25 to +125°C)	$\Delta(V_{BE1}-V_{BE2})$	 — —	 0.8 1.0	mVdc

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) The lower of the two h_{FE} readings is taken as h_{FE1} for the purpose of measurement.

2N2723

CASE 20-03, STYLE 8
TO-72 (TO-206AF)



DARLINGTON TRANSISTOR

NPN SILICON

5

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage (Base 1 and Base 2 open)	V_{CE2O}	60	Vdc
Collector-Base Voltage	V_{CB1}	80	Vdc
Emitter-Base Voltage	V_{E2B1}	12	Vdc
Collector Current — Continuous	I_C	40	Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.5 2.9	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.8 10.5	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

Refer to 2N998 for graphs.

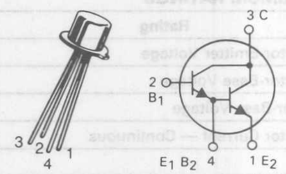
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_{B1} = 0)	$V_{(BR)CE2O}$	60	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_{E2} = 0)	$V_{(BR)CB1O}$	80	—	Vdc
Emitter-Base Breakdown Voltage (I_{E2} = 10 μAdc, I_C = 0)	$V_{(BR)E2B1O}$	12	—	Vdc
Collector Cutoff Current (V_{CB1} = 60 Vdc, I_E = 0) (V_{CB1} = 60 Vdc, I_E = 0, T_A = 150°C)	I_{CB1O}	—	 0.01 10	μAdc
Emitter Cutoff Current (V_{B1E2} = 10 Vdc, I_C = 0)	I_{E2B1O}	—	10	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 10 mAdc, V_{CE2} = 5.0 Vdc, I_{B2} = 0)	h_{FE}	2000	10,000	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_{B1} = 1.0 mAdc)	$V_{CE2(sat)}$	—	1.0	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_{B1} = 1.0 mAdc)	$V_{BE2(sat)}$	—	1.7	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance (V_{CB1} = 10 Vdc, I_{E2} = 0, f = 140 kHz)	C_{ob1o}	—	10	pF
Small-Signal Current Gain (I_C = 10 mAdc, V_{CE2} = 5.0 Vdc, f = 1.0 kHz)	h_{fe}	1500	15,000	—
Current Gain — Bandwidth Product (Each Unit) (I_C = 10 mAdc, V_{CE1} or V_{CE2} = 10 Vdc, f = 20 MHz)	$\|h_{fe}\|$	5.0	—	—
Noise Figure (Input Stage Only) (I_C = 50 μAdc, V_{CE} = 5.0 Vdc, R_S = 3.0 kohms, f = 1.0 kHz, BW = 100 Hz)	NF	—	10	dB

(1) Pulse Test: Pulse Width ≤ 12 ms, Duty Cycle ≤ 2.0%.

2N2785

CASE 20-03, STYLE 8
TO-72 (TO-206AF)



DARLINGTON TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage (Base 1 and Base 2 open)	V_{CE2O}	40	Vdc
Collector-Base Voltage	V_{CB1O}	60	Vdc
Emitter-Base Voltage (Pin 4 to Pin 2)	V_{E2B1O}	15 7.5	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.5 2.9	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.8 10.5	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

Refer to 2N998 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

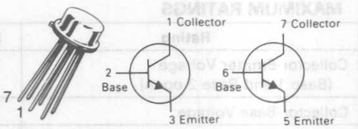
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) (I_C = 20 mAdc, I_{B1} = 0)	$V_{(BR)CEO2O}$	40	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_{E2} = 0)	$V_{(BR)CBO1O}$	60	—	Vdc
Emitter-Base Breakdown Voltage (I_{E2} = 100 μAdc, I_C = 0)	$V_{(BR)E2BO1O}$	15	—	Vdc
Collector Cutoff Current (V_{CE} = 20 Vdc, I_B = 0)	I_{CEO}	—	500	nAdc
Collector Cutoff Current (V_{CB1} = 30 Vdc, I_E = 0) (V_{CB1} = 30 Vdc, I_E = 0, T_A = 150°C)	I_{CBO}	—	 0.05 10	μAdc
Emitter Cutoff Current (V_{E2B1} = 5.0 Vdc, I_C = 0)	I_{EBO}	—	20	nAdc
ON CHARACTERISTICS				
DC Current Gain(1) (I_C = 1.0 mAdc, V_{CE2} = 4.0 Vdc) (I_C = 10 mAdc, V_{CE2} = 5.0 Vdc) (I_C = 100 mAdc, V_{CE2} = 5.0 Vdc)	h_{FE}	 600 1200 2000	— — 20,000	—
Collector-Emitter Saturation Voltage (I_C = 15 mAdc, I_{B1} = 3.0 mAdc)	$V_{CE(sat)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance (V_{CB1} = 10 Vdc, I_{E2} = 0, f = 1.0 MHz)	C_{ob1o}	—	30	pF
Input Impedance (I_C = 1.0 mAdc, V_{CB1} = 5.0 Vdc, f = 1.0 kHz)	h_{ib}	30	80	Ohms
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE2} = 5.0 Vdc, f = 1.0 kHz)	h_{rb}	—	10	$X 10^{-4}$
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE2} = 5.0 Vdc, f = 1.0 kHz)	h_{fe}	600	—	—
Current Gain — High Frequency (I_C = 1.0 mAdc, V_{CE2} = 5.0 Vdc, f = 10 MHz)	$\|h_{fe}\|$	1.0	—	—
Output Admittance (I_C = 1.0 mAdc, V_{CB1} = 5.0 Vdc, f = 1.0 kHz)	h_{ob}	—	0.5	μmhos

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

5

2N2903

CASE 654-07, STYLE 1



DUAL AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N2920 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	30		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	7.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
		One Die	Both Die	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	200 1.14	300 1.71	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	0.6 3.43	1.2 6.86	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

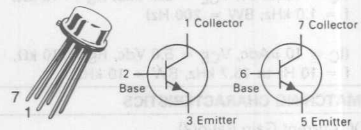
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{CEO(sus)}$	30	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 0.1\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	7.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$) ($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = 150°C$)	I_{CBO}	—	0.01 15	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0$ Vdc, $I_C = 0$)	I_{EBO}	—	0.01	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 10\ \mu$Adc, $V_{CE} = 5.0$ Vdc) ($I_C = 10\ \mu$Adc, $V_{CE} = 5.0$ Vdc, $T_A = -55°C$) ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, $T_A = -55°C$)	h_{FE}	60 25 125 60	— — 625 —	—
Collector-Emitter Saturation Voltage ($I_C = 5.0$ mAdc, $I_B = 0.5$ mAdc)	$V_{CE(sat)}$	—	1.0	Vdc
Base-Emitter Saturation Voltage ($I_C = 5.0$ mAdc, $I_B = 0.5$ mAdc)	$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 30 MHz)	f_T	60	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 140 kHz)	C_{obo}	—	8.0	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 140 kHz)	C_{ibo}	—	10	pF
Input Impedance ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz)	h_{ie}	1.0	—	kohm
Input Impedance ($I_C = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz)	h_{ib}	20	30	ohms
Voltage Feedback Ratio ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz)	h_{re}	—	6.0	$X\ 10^{-4}$
Voltage Feedback Ratio ($I_C = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz)	h_{rb}	—	5.0	$X\ 10^{-4}$
Small-Signal Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz)	h_{fe}	150	600	—
Output Admittance ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 1.0 kHz)	h_{oe}	5.0	30	μmhos
Output Admittance ($I_C = 1.0$ mAdc, $V_{CB} = 5.0$ Vdc, f = 1.0 kHz)	h_{ob}	—	0.2	μmho
Noise Figure ($I_C = 10\ \mu$Adc, $V_{CE} = 5.0$ Vdc, $R_S = 10$ kohms, f = 1.0 kHz)	NF	—	7.0	dB
MATCHING CHARACTERISTICS				
DC Current Gain Ratio(2) ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc)	h_{FE1}/h_{FE2}	0.8	1.0	—
Base-Emitter Voltage Differential ($I_C = 10\ \mu$Adc, $V_{CE} = 5.0$ Vdc)	$\lvert V_{BE1}-V_{BE2}\rvert$	—	10	mVdc
Base-Emitter Voltage Differential Gradient ($I_C = 10\ \mu$Adc, $V_{CE} = 5.0$ Vdc, $T_A = -55°C$ to $+125°C$)	$\frac{\Delta(V_{BE1}-V_{BE2})}{\Delta T_A}$	—	20	μV/°C

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) Lowest h_{FE} reading is taken as h_{FE1} for this ratio.

2N2913 thru 2N2920

JAN, JTX, JTXV, JANS AVAILABLE
CASE 654-07, STYLE 1



DUAL AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	2N2913 thru 2N2918	2N2919 2N2920	Unit
Collector-Emitter Voltage	V_{CEO}	45	60	Vdc
Collector-Base Voltage	V_{CBO}	45	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	30		mAdc
		One Die	Both Die	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 1.7	500 2.86	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	750 4.3	1500 8.6	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	2N2913 thru 18, 2N2919, 2N2920	$V_{(BR)CEO(sus)}$	45 60	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	2N2913 thru 18, 2N2919, 2N2920	$V_{(BR)CBO}$	45 60	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	6.0	—	—	Vdc
Collector Cutoff Current (V_{CE} = 5.0 Vdc, I_B = 0)		I_{CEO}	—	—	0.002	μAdc
Collector Cutoff Current (V_{CB} = 45 Vdc, I_E = 0)	2N2913 thru 18, 2N2919, 2N2920	I_{CBO}	— —	— —	0.010 0.002	μAdc
(V_{CB} = 45 Vdc, I_E = 0, T_A = 150°C)	All Types		—	—	10	
Emitter Cutoff Current (V_{EB} = 5.0 Vdc, I_C = 0)		I_{EBO}	—	—	0.002	μAdc
ON CHARACTERISTICS						
DC Current Gain(1) (I_C = 10 μAdc, V_{CE} = 5.0 Vdc)	2N2913,15,17,19, 2N2914,16,18,20	h_{FE}	60 150	— —	240 600	—
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc, T_A = −55°C)	2N2913,15,17,19, 2N2914,16,18, 2N2920		15 30 40	— — —	— — —	
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	2N2913,15,17,19, 2N2914,16,18,20		100 225	— —	— —	
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	2N2913,15,17,19, 2N2914,16,18,20		150 300	— —	— —	
Collector-Emitter Saturation Voltage (I_C = 1.0 mAdc, I_B = 0.1 mAdc)		$V_{CE(sat)}$	—	—	0.35	Vdc
Base-Emitter On Voltage (I_C = 100 μAdc, V_{CE} = 5.0 Vdc)		$V_{BE(on)}$	—	—	0.7	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product (I_C = 500 μAdc, V_{CE} = 5.0 Vdc, f = 20 MHz)		f_T	60	—	—	MHz

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 140 kHz)		C_{obo}	—	4.0	6.0	pF
Input Impedance (I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)		h_{ib}	25	28	32	ohms
Output Admittance (I_C = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)		h_{ob}	—	—	1.0	μmhos
Noise Figure (I_C = 10 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 kΩ, f = 1.0 kHz, BW = 200 Hz)	2N2914,16,18,20, 2N2913,15,17,19	NF	— —	2.0 3.0	3.0 4.0	dB
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 kΩ, f = 10 Hz to 15.7 kHz, BW = 10 kHz)	2N2914,16,18,20, 2N2913,15,17,19		— —	2.0 3.0	3.0 4.0	
MATCHING CHARACTERISTICS						
DC Current Gain Ratio(2) (I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	2N2917,18, 2N2915,16,19,20	h_{FE1}/h_{FE2}	0.8 0.9	— —	1.0 1.0	—
Base-Emitter Voltage Differential (I_C = 10 μAdc to 1.0 mAdc, V_{CE} = 5.0 Vdc)	2N2917,18, 2N2915,16,19,20	$\|V_{BE1}-V_{BE2}\|$	— —	— —	10 5.0	mVdc
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	2N2917,18, 2N2915,16,19,20		— —	— —	5.0 3.0	
Base-Emitter Voltage Differential Change Due to Temperature (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, T_A = −55°C to +25°C)	2N2917,18, 2N2915,16,19,20	$\Delta(V_{BE1}-V_{BE2})$	— —	— —	1.6 0.8	mVdc
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc, T_A = +25°C to +125°C)	2N2917,18 2N2915,16,19,20		— —	— —	2.0 1.0	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) The lowest h_{FE} reading is taken as h_{FE1} for this ratio.

FIGURE 1 — DC CURRENT GAIN versus COLLECTOR CURRENT

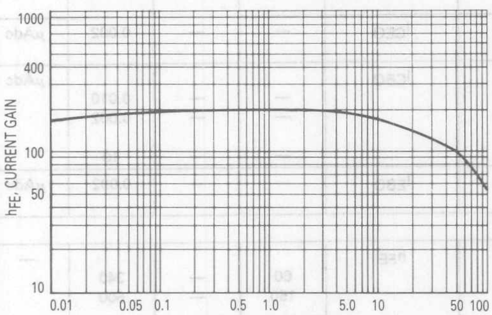


FIGURE 2 — DC CURRENT GAIN versus COLLECTOR CURRENT

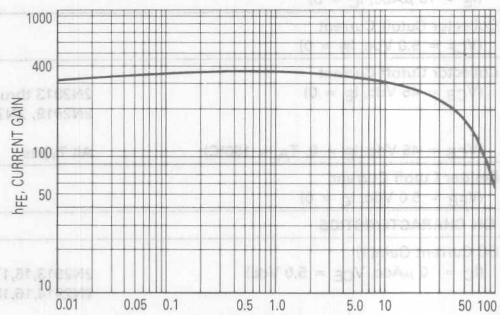


FIGURE 3 — "ON" VOLTAGES

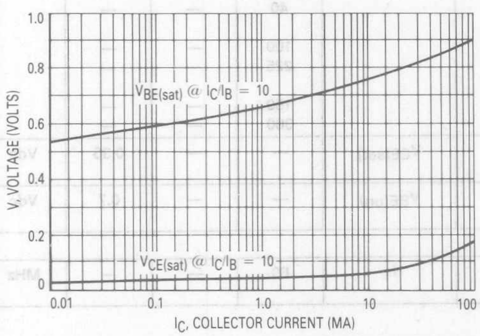
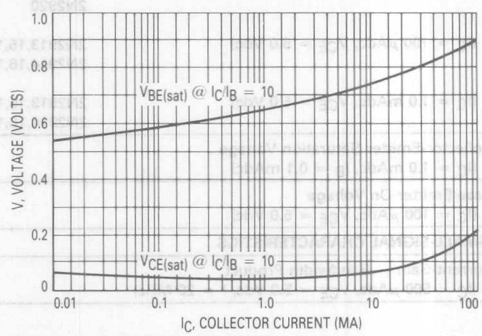
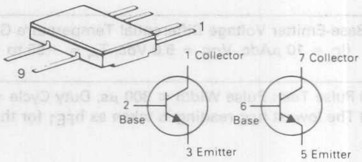


FIGURE 4 — "ON" VOLTAGES



2N3043
thru
2N3045
2N3048

CASE 610A-04, STYLE 1



DUAL AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	45		Vdc
Collector-Base Voltage	V_{CBO}	45		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	30		mAdc
		One Die	Both Die	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	250 1.67	350 2.33	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	0.7 4.67	1.4 9.33	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)		$V_{(BR)CEO}$	45	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 45 Vdc, I_E = 0) (V_{CB} = 45 Vdc, I_E = 0, T_A = +150°C)		I_{CBO}	 — —	 0.010 10	μAdc
Emitter Cutoff Current (V_{EB} = 4.0 Vdc, I_C = 0)		I_{EBO}	—	0.010	μAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 10 μAdc, V_{CE} = 5.0 Vdc) (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	 2N3043, 2N3044, 2N3045 2N3048 2N3043, 2N3044, 2N3045 2N3048	h_{FE}	 100 50 130 65	 300 200 — —	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 0.5 mAdc)		$V_{CE(sat)}$	—	1.0	Vdc
Base-Emitter On Voltage (I_C = 10 mAdc, V_{CE} = 5.0 Vdc)		V_{BE}	0.6	0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 20 MHz)		f_T	30	—	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	8.0	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	 2N3043, 2N3044, 2N3045 2N3048	h_{ie}	 3.2k 1.6k	 19k 13k	Ohms
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	 2N3043, 2N3044, 2N3045 2N3048	h_{fe}	 130 65	 600 400	—
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)		h_{oe}	 — —	 100 70	μmhos
Noise Figure (I_C = 10 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 kohms, Bandwidth = 10 Hz to 15.7 kHz)		NF	—	5.0	dB

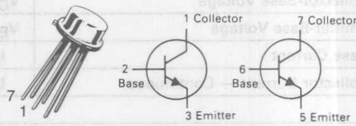
Characteristic		Symbol	Min	Max	Unit
MATCHING CHARACTERISTICS					
DC Current Gain Ratio(2)		h_{FE1}/h_{FE2}			—
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc)	2N3043		0.9	1.0	
	2N3044		0.8	1.0	
Base-Emitter Voltage Differential		$\lvert V_{BE1}-V_{BE2}\rvert$			mVdc
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc)	2N3043		—	5.0	
	2N3044		—	10	
Base-Emitter Voltage Differential Temperature Gradient		$\frac{\Delta(V_{BE1}-V_{BE2})}{\Delta T_A}$			μV/°C
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc, T_A = −55 to +125°C)	2N3043		—	10	
	2N3044		—	20	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) The lowest h_{FE} reading is taken as h_{FE1} for this test.

5

2N3425

CASE 654-07, STYLE 1



DUAL AMPLIFIER TRANSISTORS

NPN SILICON

Refer to MD2369,A,B for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	15		Vdc
Collector-Emitter Voltage	V_{CER}	20		Vdc
Collector-Base Voltage	V_{CBO}	40		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
		One Die	Both Die	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.3 1.72	0.4 2.28	Watt mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	0.75 4.3	1.5 8.55	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

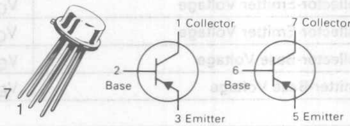
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 30$ mAdc, $R_{BE} \leq 10$ ohms)	$V_{CER(sus)}$	20	—	Vdc
Collector-Emitter Sustaining Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{CEO(sus)}$	15	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 20$ Vdc, $V_{EB(off)} = 0.25$ Vdc, $T_A = 125°C$)	I_{CEX}	—	15	μAdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$) ($V_{CB} = 20$ VDc, $I_E = 0$, $T_A = 150°C$)	I_{CBO}	— —	0.025 15	μAdc
Emitter Cutoff Current ($V_{EB} = 4.0$ Vdc, $I_C = 0$)	I_{EBO}	—	0.2	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 0.5$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc, $T_A = -55°C$)	h_{FE}	12 30 12	— 120 —	
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 7.0$ mAdc, $I_B = 0.7$ mAdc, $T_A = -55°C$ to $+125°C$)	$V_{CE(sat)}$		 0.4 0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 7.0$ mAdc, $I_B = 0.7$ mAdc, $T_A = -55°C$)	$V_{BE(sat)}$	0.7	0.85 0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 20$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	300	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 140 kHz)	C_{obo}	—	6.0	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 140 kHz)	C_{ibo}	—	9.0	pF
Small-Signal Current Gain ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc, f = 1.0 kHz)	h_{fe}	20	—	—
Real Part of Input Impedance ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 300 MHz)	$Re(h_{ie})$	—	50	Ohms
SWITCHING CHARACTERISTICS				
Storage Time ($I_C = 10$ mAdc, $I_{B1} = 10$ mAdc, $I_{B2} = 10$ mAdc)	t_s	—	40	ns
Turn-On Time ($V_{CC} = 3.0$ Vdc, $V_{EB(off)} = 2.0$ Vdc, $I_C = 10$ mAdc, $I_{B1} = 3.0$ mAdc)	t_{on}	—	50	ns
Turn-Off Time ($V_{CC} = 3.0$ Vdc, $I_C = 10$ mAdc, $I_{B1} = 3.0$ mAdc, $I_{B2} = 1.0$ mAdc)	t_{off}	—	90	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 1.0%.

5

2N3726
2N3727

CASE 654-07, STYLE 1



DUAL AMPLIFIER TRANSISTOR

PNP SILICON

5

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	45		Vdc
Collector-Base Voltage	V_{CBO}	45		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Base Current	I_B	100		mAdc
Collector Current — Continuous	I_C	300		mAdc
		One Die	Both Die	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	400 2.29	500 2.86	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	0.85 4.85	1.4 8.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C
Collector$_1$ to Collector$_2$ Voltage Voltage rating any lead to case	$V_{C1}\ V_{C2}$	±200 ±200		Vdc Vdc

Refer to MD2905,A for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	45	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.01$ mAdc, $I_E = 0$)	$V_{(BR)CBO}$	45	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 0.01$ mAdc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$) ($V_{CB} = 30$ Vdc, $I_E = 0$, $T_A = 150°C$)	I_{CBO}	 — —	 10 10	 nAdc μAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 0.01$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 0.1$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 50$ mAdc, $V_{CE} = 5.0$ Vdc)(1)	h_{FE}	 80 120 135 115	 — — 350 —	—
Collector-Emitter Saturation Voltage(1) ($I_C = 50$ mAdc, $I_B = 2.5$ mAdc)	$V_{CE(sat)}$	—	0.25	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 50$ mAdc, $I_B = 2.5$ mAdc)	$V_{BE(sat)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product(2) ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz) ($I_C = 50$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)	f_T	 60 200	 — 600	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{obo}	—	8.0	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)	C_{ibo}	—	30	pF
Input Impedance ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{ie}	—	11.5	kohm
Voltage Feedback Ratio ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{re}	—	1500	$X\ 10^{-6}$
Small-Signal Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	135	420	—

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{oe}	—	80	μmhos
Noise Figure (I_C = 30 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 kohms, f = 1.0 kHz, B.W. = 200 Hz)		NF	—	4.0	dB
MATCHING CHARACTERISTICS					
DC Current Gain Ratio(3) (I_C = 0.1 mAdc to 1.0 mAdc, V_{CE} = 5.0 Vdc)		h_{FE1}/h_{FE2}	0.9	1.0	—
Base-Emitter Voltage Differential (I_C = 0.1 mAdc to 1.0 mAdc, V_{CE} = 5.0 Vdc)	2N3726	$\|V_{BE1}-V_{BE2}\|$	—	5.0	mVdc
	2N3727		—	2.5	
Base-Emitter Differential Change Due to Temperature (I_C = 0.1 mAdc to 1.0 mAdc, V_{CE} = 5.0 Vdc, T_A = −55°C to +25°C)	2N3726	$\Delta(V_{BE1}-V_{BE2})$	—	1.6	mVdc
	2N3727		—	0.8	
(I_C = 0.1 mAdc to 1.0 mAdc, V_{CE} = 5.0 Vdc, T_A = +25°C to +125°C)	2N3726		—	2.0	
	2N3727		—	1.0	

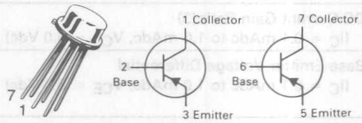
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.
(3) For purposes of this ratio, the lowest h_{FE} reading is taken as h_{FE1}.

5

5

2N3810,A
2N3811,A

CASE 654-07, STYLE 1



2N3810, 2N3811 — JAN, JTX, JTXV AVAILABLE

DUAL AMPLIFIER TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	60		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
		One Die	Both Die	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	500 2.86	600 3.43	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)		$V_{(BR)CEO}$	60	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0) (V_{CB} = 50 Vdc, I_E = 0, T_A = 150°C)		I_{CBO}	 — —	 0.01 10	μAdc
Emitter Cutoff Current (V_{BE} = 4.0 Vdc, I_C = 0)		I_{EBO}	—	20	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 1.0 μAdc, V_{CE} = 5.0 Vdc)	 2N3807,9,11,A	h_{FE}	 75	 —	—
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc)	2N3806,8,10,A 2N3807,9,11,A		100 225	— —	
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	2N3806,8,10,A 2N3807,9,11,A		150 300	450 900	
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc, T_A = −55°C)	2N3806,8,10,A 2N3807,9,11,A		75 150	— —	
(I_C = 500 μAdc, V_{CE} = 5.0 Vdc)	2N3806,8,10,A 2N3807,9,11,A		150 300	450 900	
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	2N3806,8,10,A 2N3807,9,11,A		150 300	450 900	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	2N3806,8,10,A 2N3807,9,11,A		125 250	— —	
Collector-Emitter Saturation Voltage(1) (I_C = 100 μAdc, I_B = 1.0 μA) (I_C = 1.0 mAdc, I_B = 100 μAdc)		$V_{CE(sat)}$	 — —	 0.2 0.25	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 100 μAdc, I_B = 10 μAdc) (I_C = 1.0 mAdc, I_B = 100 μAdc)		$V_{BE(sat)}$	 — —	 0.7 0.8	Vdc

Characteristic		Symbol	Min	Max	Unit
Base-Emitter On Voltage (I_C = 100 μAdc, V_{CE} = 5.0 Vdc)		$V_{BE(on)}$	—	0.7	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 500 μAdc, V_{CE} = 5.0 Vdc, f = 30 MHz) (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)		f_T	 30 100	 — 500	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	4.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	8.0	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	 2N3806,8,10,A 2N3807,9,11,A	h_{ie}	 3.0 10	 30 40	kΩ
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{re}	—	25	X 10^{-4}
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	 2N3806,8,10,A 2N3807,9,11,A	h_{fe}	 150 300	 600 900	—
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{oe}	5.0	60	μmhos
Noise Figure (I_C = 100 μAdc, V_{CE} = 10 Vdc, R_G = 3.0 kohms f = 100 Hz, BW = 20 Hz	 2N3806,8,10,A 2N3807,9,11,A	NF	 — —	 7.0 4.0	dB
Spot Noise f = 1.0 kHz, BW = 200 Hz	2N3806,8,10,A 2N3807,9,11,A		— —	3.0 1.5	
f = 10 kHz, BW = 2.0 kHz)	2N3806,8,10,A 2N3807,9,11,A		— —	2.5 1.5	
Broadband Noise Bandwidth 10 Hz to 15.7 kHz	2N3806,8,10,A 2N3807,9,11,A		— —	3.5 2.5	
MATCHING CHARACTERISTICS					
DC Current Gain Ratio(2) (I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	 2N3808,9 2N3810,11 2N3810A,11A	h_{FE1}/h_{FE2}	 0.8 0.9 0.95	 1.0 1.0 1.0	—
(I_C = 100 μAdc, V_{CE} = 50 Vdc, T_A = −55 to +125°C)	2N3810A,11A		0.85	1.0	
Base-Emitter Voltage Differential (I_C = 10 μAdc to 10 mAdc, V_{CE} = 5.0 Vdc)	 2N3808,9 2N3810,A,11,A	$\|V_{BE1}-V_{BE2}\|$	 — —	 8.0 5.0	mVdc
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	2N3808,9 2N3810,11 2N3810A,11A		— — —	5.0 3.0 1.5	
Base-Emitter Voltage Differential Change Due to Temperature (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, T_A = −55 to +25°C)	 2N3808,9 2N3810,11 2N3810A,11A	$\Delta(V_{BE1}-V_{BE2})$	 — — —	 1.6 0.8 0.4	mVdc
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc, T_A = +25 to +125°C)	2N3808,9 2N3810,11 2N3810A,11A		— — —	2.0 1.0 0.5	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) The lowest h_{FE} reading is taken as h_{FE1} for this ratio.

5

FIGURE 1 — DC CURRENT GAIN versus COLLECTOR CURRENT

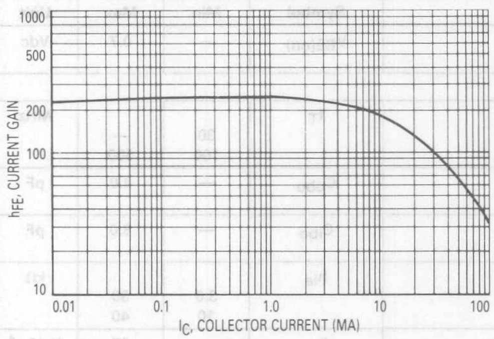


FIGURE 2 — DC CURRENT GAIN versus COLLECTOR CURRENT

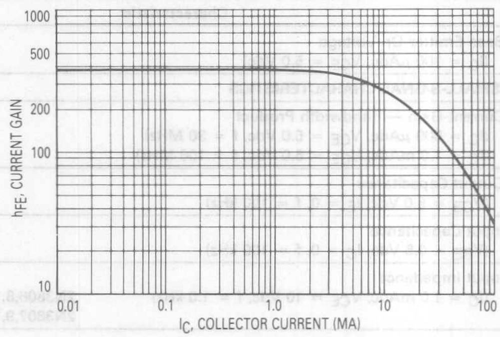


FIGURE 3 — "ON" VOLTAGES

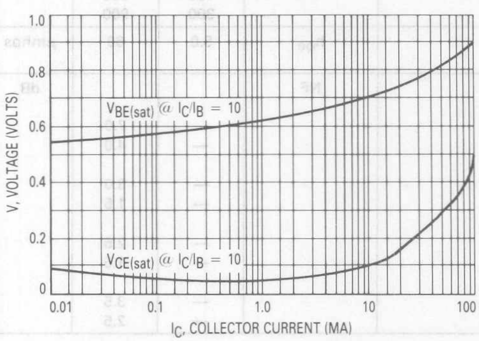
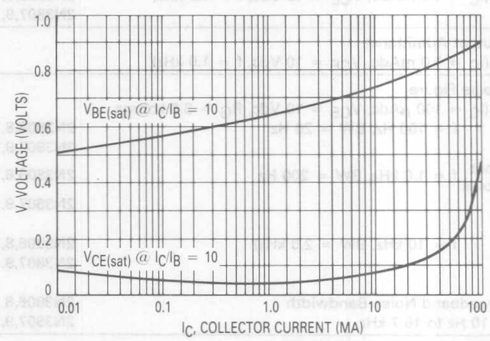
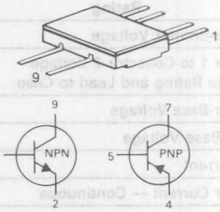


FIGURE 4 — "ON" VOLTAGES



2N3838

CASE 610A-04, STYLE 1



COMPLEMENTARY DUAL AMPLIFIER TRANSISTOR

NPN/PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector 1 to Collector 2 Voltage Voltage Rating any Lead to Case	V_{C1C2}	±120 ±120		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	600		mAdc
		One Die	Both Die	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.25 1.67	0.35 2.34	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	0.7 4.67	1.4 9.34	Watts
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

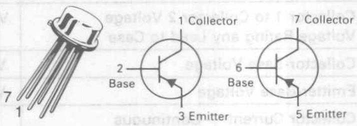
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)		$V_{(BR)CEO}$	40	—	Vdc
Collector-Emitter Nonmatching Voltage ($I_{C(on)}$ = 600 mAdc, $I_{B(on)}$ = 120 mAdc, $I_{B(off)}$ = 0)		$V_{CEO(NL)}$†	40	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Base Cutoff Current (V_{CE} = 50 Vdc, $V_{BE(off)}$ = 0.5 Vdc)		I_{BEV}	—	10	nAdc
Collector Cutoff Current (V_{CE} = 50 Vdc, $V_{BE(off)}$ = 0.5 Vdc) (V_{CE} = 50 Vdc, $V_{BE(off)}$ = 0.5 Vdc, T_A = 150°C)		I_{CEV}	— —	0.01 10	μAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)		I_{EBO}	—	10	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 0.1 mAdc, V_{CE} = 10 Vdc) (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc)(1) (I_C = 150 mAdc, V_{CE} = 10 Vdc)(1) (I_C = 150 mAdc, V_{CE} = 1.0 Vdc)(1)		h_{FE}	35 50 75 100 50	— — — 300 —	—
Collector-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc)		$V_{CE(sat)}$	—	0.4	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc)		$V_{BE(sat)}$	0.85	1.3	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	200	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 140 kHz)		C_{obo}	—	8.0	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{ie}	1.6	9.0	kohms
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{fe}	60	300	—
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{oe}	—	50	μmho
Noise Figure (I_C = 100 μAdc, V_{CE} = 10 Vdc, R_S = 1.0 kohm, f = 1.0 kHz)		NF	—	8.0	dB
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 10 Vdc, $V_{BE(off)}$ = 0 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_d	—	10	ns
Rise Time		t_r	—	40	ns
Storage Time	(V_{CC} = 10 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_s	—	250	ns
Fall Time		t_f	—	90	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

† The highest value of collector supply voltage that may be safely used with a resistive load switching circuit in which the collector current is 600 mAdc.

2N4016

CASE 654-07, STYLE 1



DUAL AMPLIFIER TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	60		Vdc
Collector 1 to Collector 2 Voltage Voltage Rating and Lead to Case	V_{C1C2}	±200 ±200		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Base Current	I_B	100		mAdc
Collector Current — Continuous	I_C	300		mAdc
		One Die	Both Die	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	400 2.29	500 2.86	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	0.85 4.85	1.4 8.0	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

Refer to MD2905,A for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	60	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$) ($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = +150°C$)	I_{CBO}	— —	10 10	nAdc μAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 0.01$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 0.1$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 50$ mAdc, $V_{CE} = 5.0$ Vdc)(1)	h_{FE}	 80 120 135 115	 — — 350 —	—
Collector-Emitter Saturation Voltage(1) ($I_C = 50$ mAdc, $I_B = 2.5$ mAdc)	$V_{CE(sat)}$	—	0.25	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 50$ mAdc, $V_{CE} = 2.5$ Vdc)	$V_{BE(sat)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product(2) ($I_C = 50$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz) ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc, f = 20 MHz)	f_T	 200 60	 600 —	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{obo}	—	8.0	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)	C_{ibo}	—	25	pF
Input Impedance ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{ie}	—	11.5	kohms
Voltage Feedback Ratio ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{re}	—	15	$X\ 10^{-4}$
Small-Signal Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc, f = 1.0 kHz)	h_{fe}	135	420	

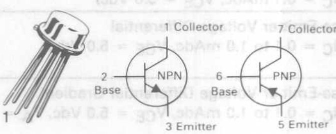
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{oe}	—	80	μmhos
Noise Figure (I_C = 0.03 mAdc, V_{CE} = 5.0 Vdc, R_S = 10 kohms, f = 1.0 kHz, BW = 200 Hz)		NF	—	4.0	dB
MATCHING CHARACTERISTICS					
DC Current Gain Ratio (I_C = 0.1 mAdc, V_{CE} = 5.0 Vdc)		h_{FE1}/h_{FE2}	0.9	1.0	—
Base-Emitter Voltage Differential (I_C = 0.1 to 1.0 mAdc, V_{CE} = 5.0 Vdc)	2N4015	$\lvert V_{BE1}-V_{BE2}\rvert$	—	5.0	mVdc
	2N4016		—	2.5	
Base-Emitter Voltage Differential Gradient (I_C = 0.1 to 1.0 mAdc, V_{CE} = 5.0 Vdc, T_A = −55 to +25°C)	2N4015	$\frac{\Delta(V_{BE1}-V_{BE2})}{\Delta T_A}$	—	1.6	mVdc
	2N4016		—	0.8	
(I_C = 0.1 to 1.0 mAdc, V_{CE} = 5.0 Vdc, T_A = +25°C to +125°C)	2N4015		—	2.0	
	2N4016		—	1.0	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 1.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

2N4854
2N4855

2N4854 — JAN, JTX, JTXV AVAILABLE
CASE 654-07, STYLE 5



COMPLEMENTARY DUAL AMPLIFIER TRANSISTOR

NPN/PNP SILICON

Refer to MD6001 for graphs.

5

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector 1 to Collector 2 Voltage Voltage Rating any Lead to Case	V_{C1C2}	±200 ±200		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	600		mAdc
		One Die	**Both Die**	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	300 2.0	600 4.0	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.0 6.67	2.0 13.33	Watts
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)		$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = 150°C$)		I_{CBO}	—	10	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)		I_{EBO}	—	10	nAdc
ON CHARACTERISTICS					
DC Current Gain		h_{FE}			—
($I_C = 0.1$ mAdc, $V_{CE} = 10$ Vdc)	2N4854 2N4855		35 20	— —	
($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc)	2N4854 2N4855		50 25	— —	
($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc)(1)	2N4854 2N4855		75 35	— —	
($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)(1)	2N4854 2N4855		100 40	300 120	
($I_C = 150$ mAdc, $V_{CE} = 1.0$ Vdc)(1)	2N4854 2N4855		50 20	— —	
($I_C = 300$ mAdc, $V_{CE} = 10$ Vdc)(1)	2N4854 2N4855		35 20	— —	
Collector-Emitter Saturation Voltage(1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc)		$V_{CE(sat)}$	—	0.4	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 150$ mAdc, $I_B = 15$ mAdc)		$V_{BE(sat)}$	0.75	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 20$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)		f_T	200	—	MHz

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

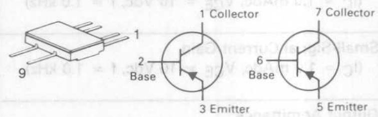
Characteristic		Symbol	Min	Max	Unit
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{cb}	—	8.0	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N4854	h_{ie}	1.5	9.0	kohms
	2N4855		0.75	4.5	
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N4854	h_{fe}	60	300	—
	2N4855		30	150	
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N4854	h_{oe}	—	50	μmhos
	2N4855		—	25	
Noise Figure (I_C = 100 μAdc, V_{CE} = 10 Vdc, R_S = 1.0 kohm, f = 1.0 kHz)		NF	—	8.0	dB
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 30 Vdc, $V_{BE(off)}$ = 0.5 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_d	—	20	ns
Rise Time		t_r	—	40	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_s	—	280	ns
Fall Time		t_f	—	70	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

5

2N4937
2N4938
2N4939

CASE 654-07, STYLE 1



2N4941

CASE 610A-04, STYLE 1

DUAL AMPLIFIER TRANSISTOR

PNP SILICON

Refer to MD3250,A for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector 1 to Collector 2 Voltage Voltage Rating and Lead to Case	V_{C1C2}	±200 ±200		Vdc
Collector-Base Voltage	V_{CBO}	50		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Base Current	I_B	10		mAdc
Collector Current — Continuous	I_C	50		mAdc
		One Die	**Both Die**	
Total Device Dissipation @ T_A = 25°C — Ceramic Metal Can Derate above 25°C — Ceramic Metal Can	P_D	 250 500 1.5 2.9	 350 600 2.0 3.4	 mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C Metal Can	P_D	 1.2 6.85	 2.0 11.42	 Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	50	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 40 Vdc, I_E = 0)	I_{CBO}	—	20	nAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)	I_{EBO}	—	20	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 100 μAdc, V_{CE} = 10 Vdc) (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc)	h_{FE}	 40 50 50	 200 250 250	—
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 Mhz)	f_T	300	900	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 140 kHz) Emitter Guarded	C_{cb}	—	5.0	pF
Input Impedance (I_{BE} = 0.5 Vdc, I_C = 0, f = 140 kHz) Collector Guarded	C_{eb}	—	10	pF
Input Impedance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{ie}	1.0	10	kΩ
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{re}	—	10	$X\ 10^{-4}$
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{fe}	50	—	—
Output Admittance (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{oe}	5.0	50	μmhos
Noise Figure (I_C = 100 μAdc, V_{CE} = 10 Vdc, R_S = 3.0 kΩ, f = 10 Hz to 15.7 kHz)	NF	—	4.0	dB

Characteristic		Symbol	Min	Max	Unit
MATCHING CHARACTERISTICS					
DC Current Gain Ratio(1)		h_{FE1}/h_{FE2}			—
(I_C = 100 μAdc to 1.0 mAdc, V_{CE} = 10 Vdc)	2N4937, 2N4941		0.9	1.0	
	2N4938		0.8	1.0	
(I_C = 100 μAdc to 1.0 mAdc, V_{CE} = 10 Vdc, T_A = −55°C to 125°C)	2N4937, 2N4941		0.85	1.0	
	2N4938		0.7	1.0	
Base-Emitter Voltage Differential		$\lvert V_{BE1}-V_{BE2}\rvert$			mVdc
(I_C = 100 μAdc to 1.0 mAdc, V_{CE} = 10 Vdc)	2N4937, 2N4941		—	3.0	
	2N4938		—	5.0	
Base-Emitter Voltage Differential Gradient		$\dfrac{\Delta(V_{BE1}-V_{BE2})}{\Delta T_A}$			mVdc
(I_C = 100 μAdc to 1.0 mAdc, V_{CE} = 10 Vdc, T_A = 25°C to +125°C)	2N4937, 2N4941		—	1.0	
	2N4938		—	2.0	
(I_C = 100 μAdc to 1.0 mAdc, V_{CE} = 10 Vdc, T_A = −55°C to 25°C)	2N4937, 2N4941		—	0.8	
	2N4938		—	1.6	

(1) The lowest h_{FE} reading is taken as h_{FE1} for this ratio.

5

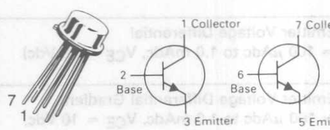
5

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CBO}	75		Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	600		mAdc
		One Die	Both Die Equal Power	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	500 2.9	600 3.4	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.2 6.9	2.0 11.43	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

2N5793
2N5794

JAN, JTX, JTXV AVAILABLE
CASE 654-07, STYLE 1



DUAL TRANSISTOR

NPN SILICON

Refer to MD2218,A for graphs.

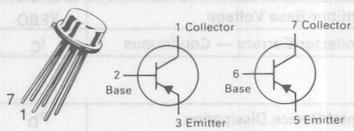
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)		$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	75	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0)		I_{CBO}	—	10	nAdc
Emitter Cutoff Current (V_{EB} = 4.0 Vdc, I_C = 0)		I_{EBO}	—	10	nAdc
Collector 1 to Collector 2 Leakage Current (V_{1C-2C} = ± 50 Vdc)		I_{C1-C2}	—	±1.0	nAdc
ON CHARACTERISTICS					
DC Current Gain		h_{FE}			—
(I_C = 100 μAdc, V_{CE} = 10 Vdc)	2N5793 2N5794		20 35	— —	
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)	2N5793 2N5794		25 50	— —	
(I_C = 10 mAdc, V_{CE} = 10 Vdc)(1)	2N5793 2N5794		35 75	— —	
(I_C = 150 mAdc, V_{CE} = 1.0 Vdc)(1)	2N5793 2N5794		20 50	— —	
(I_C = 150 mAdc, V_{CE} = 10 Vdc)(1)	2N5793 2N5794		40 100	120 300	
(I_C = 300 mAdc, V_{CE} = 10 Vdc)(1)	2N5793 2N5794		25 40	— —	
Collector-Emitter Saturation Voltage(1)	(I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 300 mAdc, I_B = 30 mAdc)	$V_{CE(sat)}$	— —	0.3 0.9	Vdc
Base-Emitter Saturation Voltage(1)	(I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 300 mAdc, I_B = 30 mAdc)	$V_{BE(sat)}$	0.6 —	1.2 1.8	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)		f_T	250	—	MHz
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{cb}	—	8.0	pF
Emitter-Base Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{eb}	—	25	pF
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 30 Vdc, $V_{BE(off)}$ = 0.5 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_d	—	15	ns
Rise Time		t_r	—	30	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_s	—	250	ns
Fall Time		t_f	—	60	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

2N5795
2N5796

JAN, JTX, JTXV AVAILABLE
CASE 654-07, STYLE 1



DUAL TRANSISTOR

PNP SILICON

Refer to MD2904,A for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	60		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	600		mAdc
		One Die	Both Die Equal Power	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	500 2.9	600 3.4	mW mW/°C
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.2 6.9	2.0 11.43	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

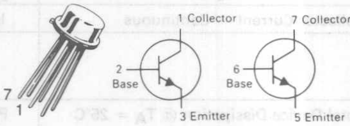
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)		$V_{(BR)CEO}$	60	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0)		I_{CBO}	—	20	nAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)		I_{EBO}		100	nAdc
Collector 1 to Collector 2 Leakage Current (V_{1C-2C} = ±50 Vdc		I_{C1-C2}	—	±1.0	nAdc
ON CHARACTERISTICS					
DC Current Gain		h_{FE}			—
(I_C = 100 μAdc, V_{CE} = 10 Vdc)	2N5795		40	—	
	2N5796		75	—	
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)	2N5795		40	—	
	2N5796		100	—	
(I_C = 10 mAdc, V_{CE} = 10 Vdc)(1)	2N5795		40	—	
	2N5796		100	—	
(I_C = 150 mAdc, V_{CE} = 1.0 Vdc)(1)	2N5795		20	—	
	2N5796		50	—	
(I_C = 150 mAdc, V_{CE} = 10 Vdc)(1)	2N5795		40	120	
	2N5796		100	300	
(I_C = 500 mAdc, V_{CE} = 10 Vdc)(1)	2N5795		40		
	2N5796		50		
Collector-Emitter Saturation Voltage(1)	(I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)	$V_{CE(sat)}$	— —	0.4 1.6	Vdc
Base-Emitter Saturation Voltage(1)	(I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)	$V_{BE(sat)}$	— —	1.3 2.6	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 50 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)		f_T	200	—	MHz
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{cb}	—	8.0	pF
Emitter-Base Capacitance (V_{EB} = 2.0 Vdc, I_C = 0, f = 100 kHz)		C_{eb}	—	30	pF
SWITCHING CHARACTERISTICS (See Figure 1)					
Delay Time	(V_{CC} = 30 Vdc, $V_{BE(off)}$ = 0.5 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_d	—	12	ns
Rise Time		t_r	—	35	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_s	—	100	ns
Fall Time		t_f	—	40	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

2N6502

CASE 654-07, STYLE 1



DUAL SWITCHING TRANSISTOR

NPN SILICON

5

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CES}	80		Vdc
Collector-Base Voltage	V_{CBO}	80		Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	1.0		Adc
		One Die	**All Die Equal Power**	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	600 3.42	650 3.7	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	2.1 12	3.0 17.2	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	58.3	°C/W
Thermal Resistance, Junction to Ambient(1)	$R_{\theta JA}$	292	270	°C/W
		Junction to Ambient	**Junction to Case**	
Coupling Factor		85	40	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 100\ \mu$Adc, $V_{BE} = 0$)	$V_{(BR)CES}$	80	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	80	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 40$ Vdc, $I_E = 0$)	I_{CBO}	—	1.7	μAdc

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Emitter Cutoff Current (V_{BE} = 4.0 Vdc, I_C = 0)	I_{EBO}	—	1.0	μAdc
ON CHARACTERISTICS				
DC Current Gain	h_{FE}			—
(I_C = 100 mAdc, V_{CE} = 1.0 Vdc)		50	150	
(I_C = 500 mAdc, V_{CE} = 2.0 Vdc)		30	—	
(I_C = 500 mAdc, V_{CE} = 1.0 Vdc)		10	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			Vdc
(I_C = 100 mAdc, I_B = 10 mAdc)		—	0.3	
(I_C = 500 mAdc, I_B = 50 mAdc)		—	0.5	
Base-Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc)	$V_{BE(sat)}$	0.8	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	250	—	MHz
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{cb}	—	10	pF
Emitter-Base Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)	C_{eb}	—	65	pF
SWITCHING CHARACTERISTICS				
Turn-On Time (V_{CC} = 30 Vdc, V_{BE} = 3.8 Vdc, I_C = 500 mAdc, I_{B1} = 50 mAdc)	t_{on}	—	35	ns
Turn-Off Time (V_{CC} = 30 Vdc, I_C = 500 mAdc, I_{B1} = I_{B2} = 50 mAdc)	t_{off}	—	60	ns

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

5

TYPICAL DC CHARACTERISTICS

FIGURE 1 – DC CURRENT GAIN

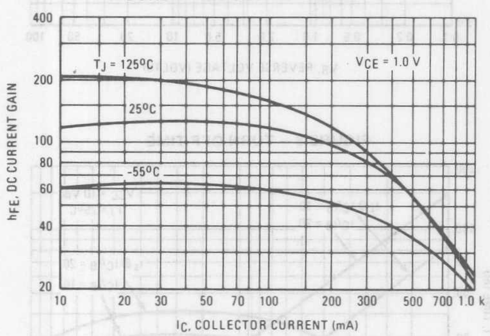


FIGURE 2 – "ON" VOLTAGES

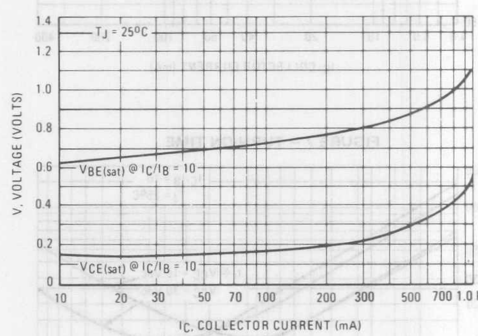


FIGURE 3 — COLLECTOR SATURATION REGION

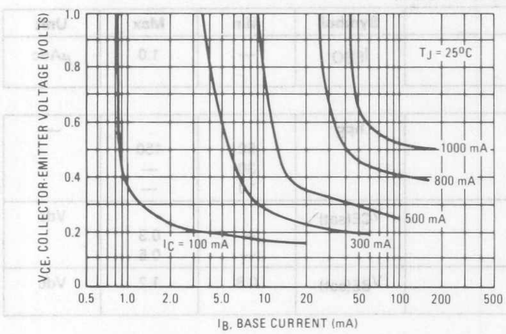
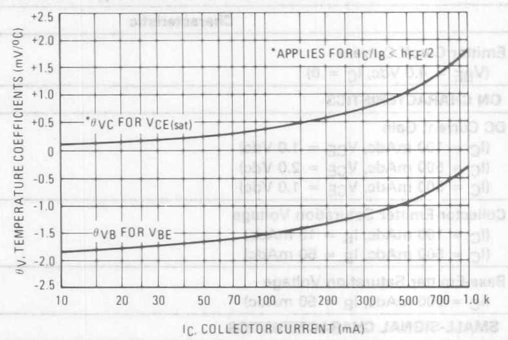


FIGURE 4 — TEMPERATURE COEFFICIENTS



TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 5 — CURRENT-GAIN — BANDWIDTH PRODUCT

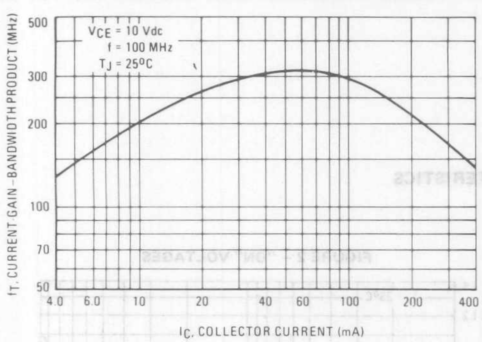


FIGURE 6 — CAPACITANCE

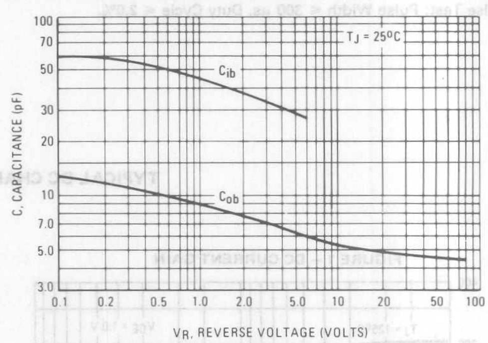


FIGURE 7 — TURN-ON TIME

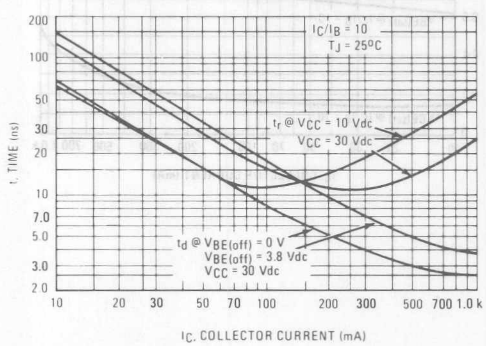


FIGURE 8 — TURN-OFF TIME

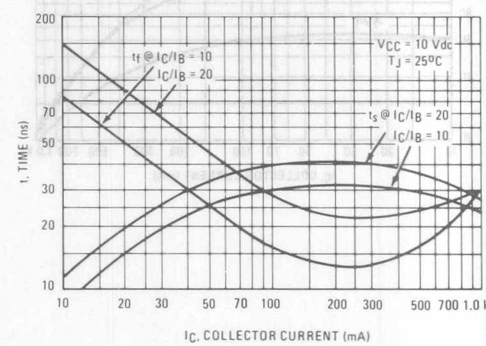


FIGURE 9 – SWITCHING TIME TEST CIRCUIT

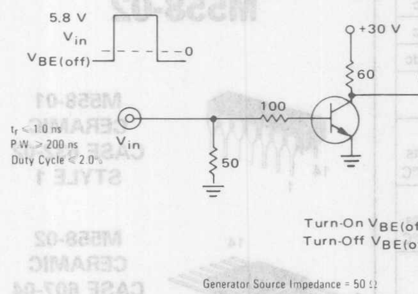
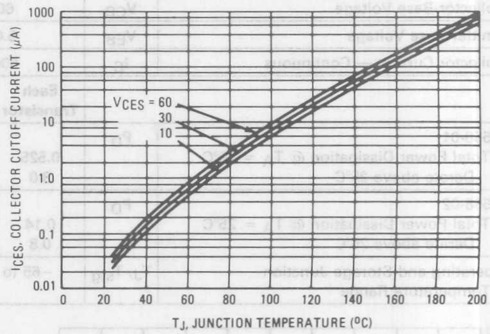
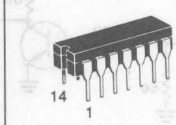


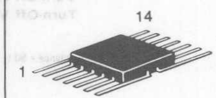
FIGURE 10 – COLLECTOR CUTOFF CURRENT



M558-01
M558-02



M558-01
CERAMIC
CASE 632-02
STYLE 1



M558-02
CERAMIC
CASE 607-04
STYLE 1

QUAD TRANSISTORS
PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	60		Vdc
Collector-Base Voltage	V_{CB}	60		Vdc
Emitter-Base Voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous	I_C	600		mAdc
		Each Transistor	Total Device	
M558-01 Total Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	 0.525 3.0	 1.5 8.57	 Watts mW/°C
M558-02 Total Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	 0.14 0.8	 0.4 2.29	 Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

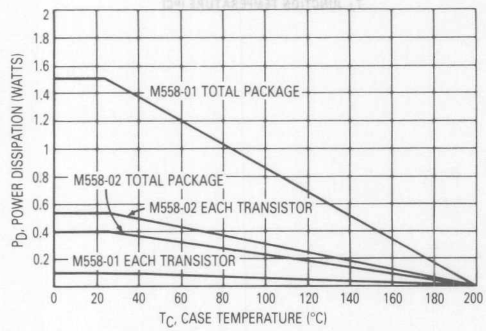


Figure 1. Power Temperature Derating Curve

Table 1. Product Classifications

JAN — Controlled Lot with Sample Environmental and Life Testing
JTX — 100% Processing Plus Sample Environmental and Life Testing
JTXV — Same as JTX Plus 100% Internal Visual Inspection

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	60	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($I_E = 0$, $V_{CB} = 60$ Vdc) ($I_E = 0$, $V_{CB} = 60$ V, $T_A = 150°C$)	I_{CBO}	 — —	 10 10	 nAdc μA
Emitter Cutoff Current ($I_C = 0$, $V_{CB} = 4.0$ Vdc)	I_{EBO}	—	10	nAdc
ON CHARACTERISTICS				
DC Current Gain(1) ($I_C = 0.1$ mA, $V_{CE} = 10$ Vdc) ($I_C = 1.0$ mA, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 500$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mA, $V_{CE} = 10$ V, $T_A = -55°C$)	h_{FE}	 75 100 100 100 50 50	 — 450 — 300 — —	
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	$V_{CE(sat)}$	 — —	 0.4 1.6	Vdc
Base-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	$V_{BE(sat)}$	 0.6 —	 1.3 2.6	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain — Bandwidth Product(1) ($I_C = 50$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)	f_T	250	800	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{obo}	—	8.0	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)	C_{ibo}	—	30	pF

Turn-On Time (V_{CC} = 30 Vdc, $V_{BE(off)}$ = 0.5 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc) (Figure 2)	t_{on}	—	45	ns
Turn-Off Time (V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc) (Figure 3)	t_{off}	—	300	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 2.0%.

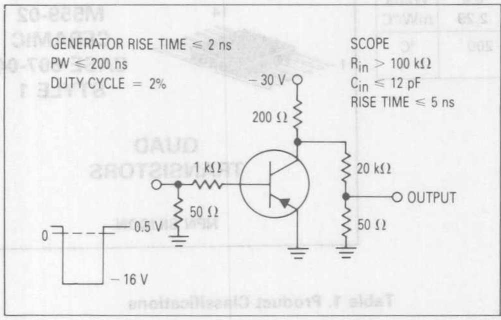


Figure 2. t_{on} Test Circuit

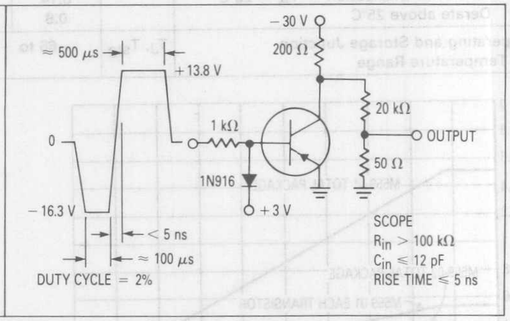


Figure 3. t_{off} Test Circuit

Table 2. JTX, JTXV 100% Processing Steps

	JTX	JTXV
Internal Visual (Mil-Std-750, Method 2072)	—	100%
High Temperature Storage (Mil-Std-750, Method 1032)	100%	100%
Thermal Shock (Mil-Std-750, Method 1051 Cond. F*)	100%	100%
Constant Acceleration (Mil-Std-750, Method 2006, 20 KG^S, Y_1)	100%	100%
Hermetic Seal (Fine + Gross Leak) (Mil-Std-750, Method 1071, Cond. G or H)**	100%	100%
READ Electrical Parameters (Group A)	100%	100%
High Temperature Reverse Bias (Mil-Std-750, Method 1039, Cond. A)	100%	100%
READ Electrical Parameters (Group A)	100%	100%
Power Burn-In (Mil-Std-750, Method 1039, Cond. B)	100%	100%
READ Electrical Parameters (Group A)	100%	100%

*$T_{(LOW)}$ = −55°C
**Cond. G, Fine Leak = 1 x 10^{-7} ATM. CC/sec.

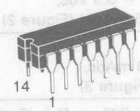
Table 3. Simplified Hi-Rel Product Flow

JAN	JTX	JTXV
Commercial Product ↓ Group A, B, C Sample Test ↓ Ship	Commercial Product ↓ 100% Test ↓ Group A, B, C Sample Test ↓ Ship	100% Pre Cap Visual ↓ 100% Test ↓ Group A, B, C Sample Test ↓ Ship

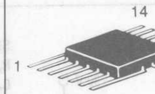
MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	50		Vdc
Collector-Base Voltage	V_{CB}	75		Vdc
Emitter-Base Voltage	V_{EB}	6.0		Vdc
Collector Current — Continuous	I_C	800		mAdc
		Each Transistor	Total Device	
M559-01 Total Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	 0.525 3.0	 1.5 8.57	 Watts mW/°C
M559-02 Total Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	 0.14 0.8	 0.4 2.29	 Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

M559-01
M559-02



M559-01
CERAMIC
CASE 632-02
STYLE 1



M559-02
CERAMIC
CASE 607-04
STYLE 1

QUAD TRANSISTORS

NPN SILICON

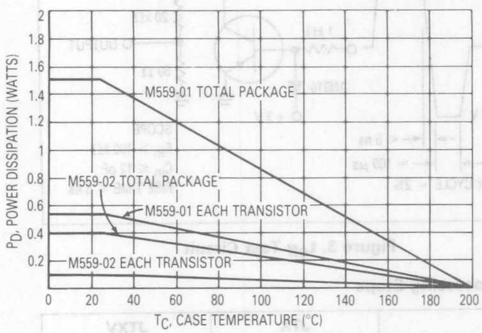


Figure 1. Power Temperature Derating Curve

Table 1. Product Classifications

JAN	— Controlled Lot with Sample Environmental and Life Testing
JTX	— 100% Processing Plus Sample Environmental and Life Testing
JTXV	— Same as JTX Plus 100% Internal Visual Inspection

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	50	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	75	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current (I_E = 0, V_{CB} = 60 Vdc) (I_E = 0, V_{CB} = 60 V, T_A = 150°C)	I_{CBO}	 — —	 10 10	 nAdc μA
Emitter Cutoff Current (I_C = 0, V_{CB} = 4.0 Vdc)	I_{EBO}	—	10	nAdc
ON CHARACTERISTICS				
DC Current Gain(1) (I_C = 0.1 mA, V_{CE} = 10 Vdc) (I_C = 1.0 mA, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc) (I_C = 150 mAdc, V_{CE} = 10 Vdc) (I_C = 500 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mA, V_{CE} = 10 V, T_A = −55°C)	h_{FE}	 50 75 100 100 30 35	 — 325 — 300 — —	
Collector-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)	$V_{CE(sat)}$	 — —	 0.3 1.0	Vdc
Base-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)	$V_{BE(sat)}$	 0.6 —	 1.2 2.0	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain — Bandwidth Product(1) (I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	250	800	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	8.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	—	25	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS				
Turn-On Time (V_{CC} = 30 Vdc, $V_{BE(off)}$ = 0.5 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc) (Figure 2)	t_{on}	—	35	ns
Turn-Off Time (V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc) (Figure 3)	t_{off}	—	300	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 2.0%.

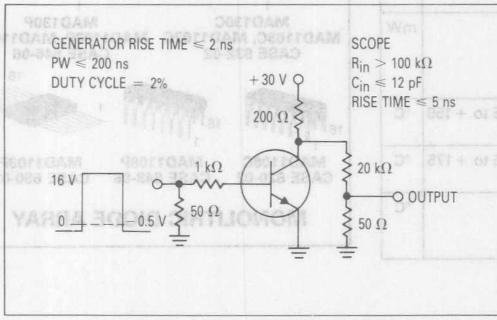


Figure 2. t_{on} Test Circuit

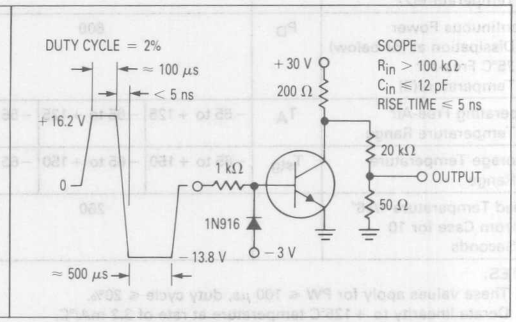


Figure 3. t_{off} Test Circuit

Table 2. JTX, JTXV 100% Processing Steps

	JTX	JTXV
Internal Visual (Mil-Std-750, Method 2072)	—	100%
High Temperature Storage (Mil-Std-750, Method 1032)	100%	100%
Thermal Shock (Mil-Std-750, Method 1051 Cond. F*)	100%	100%
Constant Acceleration (Mil-Std-750, Method 2006, 20 KGS, Y_1)	100%	100%
Hermetic Seal (Fine + Gross Leak) (Mil-Std-750, Method 1071, Cond. G or H)**	100%	100%
READ Electrical Parameters (Group A)	100%	100%
High Temperature Reverse Bias (Mil-Std-750, Method 1039, Cond. A)	100%	100%
READ Electrical Parameters (Group A)	100%	100%
Power Burn-In (Mil-Std-750, Method 1039, Cond. B)	100%	100%
READ Electrical Parameters (Group A)	100%	100%

*$T_{(LOW)}$ = −55°C
**Cond. G, Fine Leak = 1 x 10^{-7} ATM. CC/sec.

Table 3. Simplified Hi-Rel Product Flow

JAN	JTX	JTXV
Commercial Product	Commercial Product	100% Pre Cap Visual
Group A, B, C Sample Test	100% Test	100% Test
Ship	Group A, B, C Sample Test	Group A, B, C Sample Test
	Ship	Ship

MAXIMUM RATINGS (@ 25°C Free-Air Temperature unless otherwise noted.)

Rating	Symbol	MAD130	MAD1103	MAD1107 MAD1108	Unit
Peak Reverse Voltage(1)	V_{RM}	40	50	50	Vdc
Steady-State Reverse Voltage	V_R	25	25	40	Vdc
Peak Forward Current at (or below) 25°C Free-Air Temperature(1)	I_{FM}		500		mA
Continuous Forward Current at (or below) 25°C Free-Air Temperature(2)	I_F		400		mA
Continuous Power Dissipation at (or below) 25°C Free-Air Temperature(3)	P_D		600		mW
Operating Free-Air Temperature Range	T_A	−65 to +125	−65 to +125	−55 to +150	°C
Storage Temperature Range	T_{stg}	−65 to +150	−65 to +150	−65 to +175	°C
Lead Temperature 1/16″ from Case for 10 Seconds			260		°C

NOTES:
1. These values apply for PW ≤ 100 μs, duty cycle ≤ 20%.
2. Derate linearity to +125°C temperature at rate of 3.2 mA/°C.
3. Derate linearity to +125°C temperature at rate of 6.0 mW/°C.

MAD130, MAD1103
MAD1107, MAD1108

MONOLITHIC DIODE ARRAY

5

PACKAGE OPTIONS

Device	CERAMIC C Suffix Pin Connection Ref. No.	CERAMIC C Suffix Case	PLASTIC P Suffix Pin Connection Ref. No.	PLASTIC P Suffix Case	FLAT CERAMIC F Suffix Pin Connection Ref. No.	FLAT CERAMIC F Suffix Case
MAD130 Dual 10-Diode Array	3	632-02	3	646-06	—	—
MAD1103 Dual 8-Diode Array	5	632-02	5	646-06	4	606-04
MAD1107 Dual 8-Diode Array	2	632-02	2	646-06	2	607-05
MAD1108 8-Diode Array	1	620-02	1	648-06	1	650-02

ELECTRICAL CHARACTERISTICS (@ 25°C Free-Air Temperature)

Characteristic		Symbol	Limit Min	Limit Max	Unit
Reverse Breakdown Voltage(1) (I_R = 10 μA)	MAD130 MAD1103/1107/1108	$V_{(BR)}$	40 50	— —	Vdc
Static Reverse Current (V_R = 25 V) (V_R = 40 V)	MAD130 MAD1103/1107 MAD1108	I_R	— — —	0.5 0.5 0.1	μA
Static Forward Voltage (I_F = 100 mA) (I_F = 500 mA)(2)		V_F	— —	1.1 1.5	Vdc
Peak Forward Voltage(3) (I_F = 500 mA)		V_{FM}	—	5.0	Vdc

NOTES:
1. This parameter must be measured using pulse techniques. PW = 100 μs, duty cycle ≤ 20%.
2. This parameter is measured using pulse techniques. PW = 300 μs, duty cycle ≤ 2.0%. Read time is 90 μs from the leading edge of the pulse.
3. The initial instantaneous value is measured using pulse techniques. PW = 150 ns, duty cycle ≤ 2.0%, pulse rise time ≤ 10 ns. The total capacitance shunting the diode is 19 pF maximum and the equipment bandwidth is 80 MHz.

(I_F = 500 mA)	t_{fr}	20	ns
Reverse Recovery Time, Figure 2 (I_F = 200 mA, I_{RM} = 200 mA, R_L = 100 Ω, i_{rr} = 20 mA)	t_{rr}	8.0	ns

PIN CONNECTION DIAGRAMS

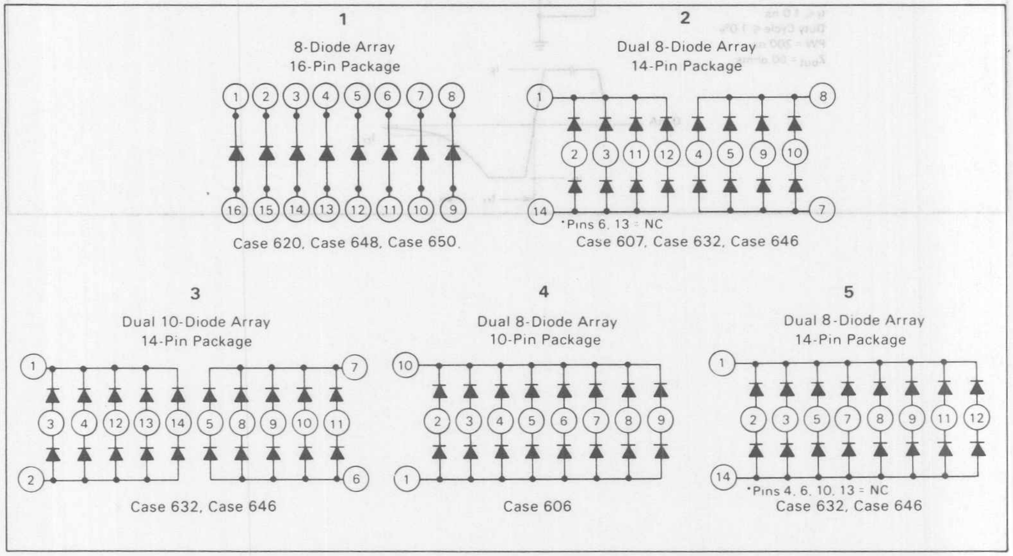


FIGURE 1 — TYPICAL CHARACTERISTICS STATIC FORWARD VOLTAGE

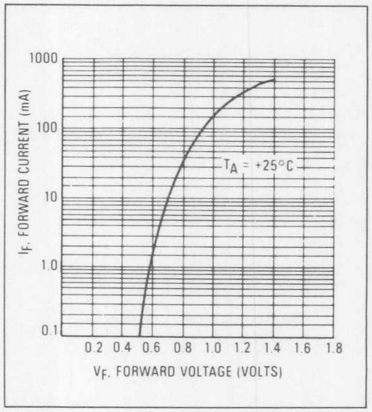


FIGURE 2 — FORWARD RECOVERY TIME AND PEAK FORWARD VOLTAGE TEST CIRCUIT AND WAVEFORMS

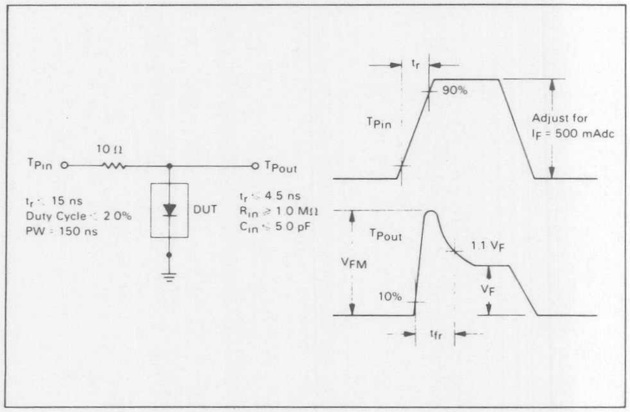
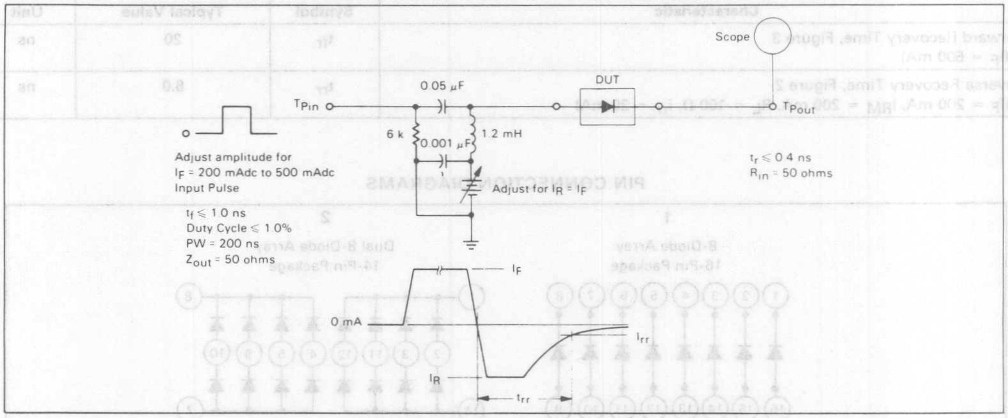
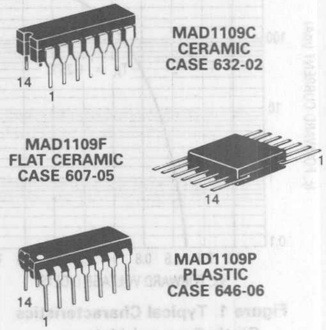


FIGURE 3 — REVERSE RECOVERY TIME TEST CIRCUIT AND WAVEFORMS



5

MAD1109



MONOLITHIC DIODE ARRAY

MAXIMUM RATINGS (@ 25°C Free-Air Temperature unless otherwise noted.)

Rating	Symbol	Value			Unit
Peak Reverse Voltage(1)	V_{RM}	50			Vdc
Steady-State Reverse Voltage	V_R	40			Vdc
Peak Forward Current at (or below) 25°C Free-Air Temperature(1)	I_{FM}	500			mA
Continuous Forward Current at (or below) 25°C Free-Air Temperature(2)	I_F	400			mA
Continuous Power Dissipation at (or below) 25°C Free-Air Temperature(3)	P_D	600			mW
		MAD1109C	MAD1109F	MAD1109P	
Operating Free-Air Temperature Range	T_A	−65 to +175	−65 to +150	−55 to +125	°C
Storage Temperature Range	T_{stg}	−65 to +200	−65 to +175	−55 to +150	°C
Lead Temperature 1/16″ from Case for 10 Seconds		260			°C

NOTES:
1. These values apply for PW ≤ 100 μs, duty cycle ≤ 20%.
2. Derate linearity to +125°C temperature at rate of 3.2 mA/°C.
3. Derate linearity to +125°C temperature at rate of 6.0 mW/°C.

ELECTRICAL CHARACTERISTICS (@ 25°C Free-Air Temperature)

Characteristic	Symbol	Limit Min	Limit Max	Unit
Reverse Breakdown Voltage(4) (I_R = 10 μA)	$V_{(BR)}$	50	—	Vdc
Static Reverse Current (V_R = 40 V)	I_R	—	0.1	μA
Static Forward Voltage (I_F = 100 mA) (I_F = 500 mA)(5)	V_F	— —	1.1 1.5	Vdc
Peak Forward Voltage(6) (I_F = 500 mA)	V_{FM}	—	5.0	Vdc

SWITCHING CHARACTERISTICS (@ 25°C Free-Air Temperature)

Characteristic	Symbol	Typical Value	Unit
Forward Recovery Time, Figure 3 (I_F = 500 mA)	t_{fr}	20	ns
Reverse Recovery Time, Figure 2 (I_F = 200 mA, I_{RM} = 200 mA, R_L = 100 Ω, i_{rr} = 20 mA)	t_{rr}	8.0	ns

NOTES:
4. This parameter must be measured using pulse techniques. PW = 100 μs, duty cycle ≤ 20%.
5. This parameter is measured using pulse techniques. PW = 300 μs, duty cycle ≤ 2.0%. Read time is 90 μs from the leading edge of the pulse.
6. The initial instantaneous value is measured using pulse techniques. PW = 150 ns, duty cycle ≤ 2.0%, pulse rise time ≤ 10 ns. The total capacitance shunting the diode is 19 pF maximum and the equipment bandwidth is 80 MHz.

5

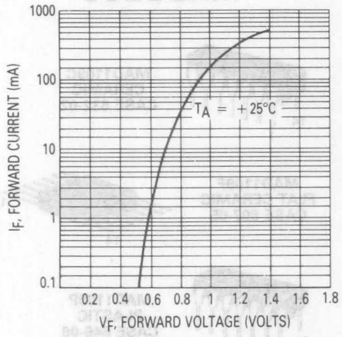


Figure 1. Typical Characteristics Static Forward Voltage

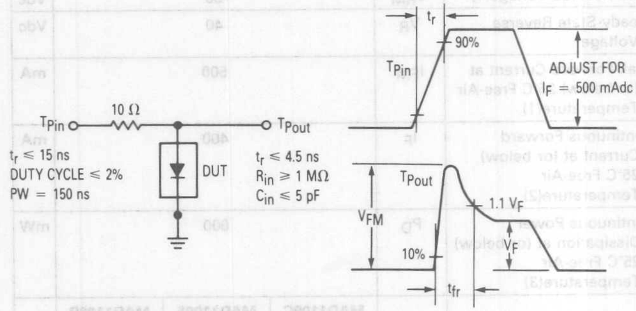


Figure 2. Forward Recovery Time and Peak Forward Voltage Test Circuit and Waveforms

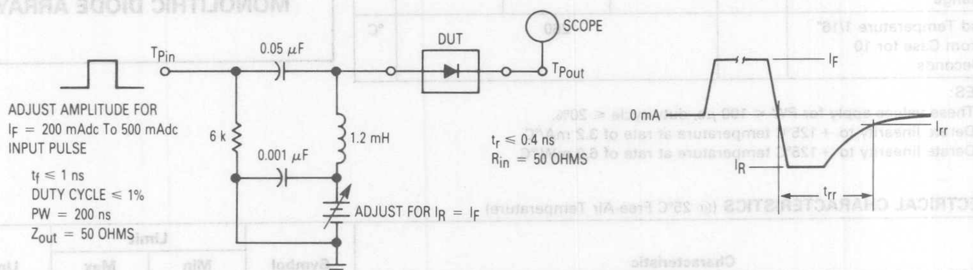
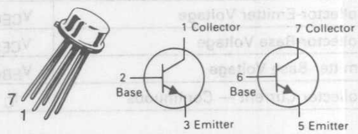


Figure 3. Reverse Recovery Time Test Circuit and Waveforms

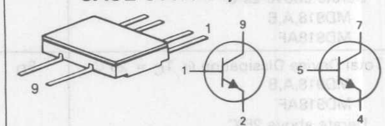
MD708,A,B

CASE 654-07, STYLE 1



MD708F,AF,BF

CASE 610A-04, STYLE 1



DUAL AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MD2369 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value: One Die	Value: Both Die Equal Power	Unit
Collector-Emitter Voltage	V_{CEO}	15		Vdc
Collector-Base Voltage	V_{CBO}	40		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
Total Device Dissipation @ $T_A = 25°C$	P_D			mW
MD708, MD708A, MD708B		550	600	
MD708F, MD708AF, MD708BF		350	400	
Derate above 25°C				mW/°C
MD708, MD708A, MD708B		3.13	3.42	
MD708F, MD708AF, MD708BF		2.0	2.28	
Total Device Dissipation @ $T_C = 25°C$	P_D			Watts
MD708, MD708A, MD708B		1.4	2.0	
MD708F, MD708AF, MD708BF		0.7	1.4	
Derate above 25°C				mW/°C
MD708, MD708A, MD708B		8.0	11.4	
MD708F, MD708AF, MD708BF		4.0	8.0	
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	One Die	Both Die Equal Power	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$			°C/W
MD708, MD708A, MD708B		125	87.5	
MD708F, MD708AF, MD708BF		250	125	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	319	292	°C/W
		500	438	
		Junction to Ambient	Junction to Case	
Coupling Factors				%
MD708, MD708A, MD708B		83	40	
MD708F, MD708AF, MD708BF		75	0	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

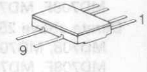
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(2) ($I_C = 30$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	15	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$)	I_{CBO}	—	15	nAdc
($V_{CB} = 20$ Vdc, $I_E = 0$, $T_A = 150°C$)		—	30	μAdc
ON CHARACTERISTICS				
DC Current Gain(2) ($I_C = 500\ \mu$Adc, $V_{CE} = 1.0$ Vdc)	h_{FE}	40	—	
($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc)		40	200	
($I_C = 100$ mAdc, $V_{CE} = 5.0$ Vdc)		35	—	
($I_C = 150$ mAdc, $V_{CE} = 5.0$ Vdc)		20	—	
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	0.20	Vdc
($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)		—	0.35	
($I_C = 100$ mAdc, $I_B = 10$ mAdc)		—	0.50	
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	0.65	0.85	Vdc
($I_C = 50$ mAdc, $I_B = 5.0$ mAdc)		—	0.95	
($I_C = 100$ mAdc, $I_B = 10$ mAdc)		—	1.10	

(2) Pulse Test: Pulse Width $\leq 300\ \mu s$, Duty Cycle $\leq 2.0\%$.

MD918
MD918A
MD918B

CASE 654-07, STYLE 1

MD918AF



CASE 610A-04, STYLE 1

DUAL
AMPLIFIER TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	15		Vdc
Collector-Base Voltage	V_{CES}	30		Vdc
Emitter-Base Voltage	V_{EBO}	3.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
		One Die	Both Die	
Total Device Dissipation @ $T_A = 25°C$	P_D			
MD918,A,B		550	600	
MD918AF		350	400	mW
Derate above 25°C				
MD918,A,B		3.14	3.42	
MD918AF		2.0	2.28	mW/°C
Total Device Dissipation @ $T_C = 25°C$	P_D			
MD918,A,B		1.4	2.0	Watts
MD918AF		0.7	1.4	
Derate above 25°C				
MD918,A,B		8.0	11.4	mW/°C
MD918AF		4.0	8.0	
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic		Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junction to Case		$R_{\theta JC}$			°C/W
	MD918,A,B		125	87.5	
	MD918AF		250	125	
Thermal Resistance, Junction to Ambient		$R_{\theta JA}$(1)			°C/W
	MD918,A,B		319	292	
	MD918AF		500	438	
			Junction to Ambient	Junction to Case	
Coupling Factors					%
	MD918,A,B		83	40	
	MD918AF		75	0	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 3.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	15	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 1.0$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	30	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	—	Vdc
Collector Cutoff Current	I_{CBO}				
($V_{CB} = 15$ Vdc, $I_E = 0$)		—	—	10	nAdc
($V_{CB} = 15$ Vdc, $I_E = 0$, $T_A = 150°C$)		—	—	1.0	μAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 3.0$ mAdc, $V_{CE} = 5.0$ Vdc)	h_{FE}	50	165	—	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ Adc)	$V_{CE(sat)}$	—	0.09	0.2	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	—	0.86	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	600	—	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	1.1	1.7	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	1.15	2.0	pF
Noise Figure (I_C = 1.0 mAdc, V_{CE} = 6.0 Vdc, R_S = 400Ω, f = 60 MHz)		NF	—	—	6.0	dB
MATCHING CHARACTERISTICS						
DC Current Gain Ratio(3) (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	MD918B MD918A,AF	h_{FE1}/h_{FE2}	0.8 0.9	— —	1.0 1.0	—
Base-Emitter Voltage Differential (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	MD918B MD918A,AF	$\lvert V_{BE1}-V_{BE2}\rvert$	— —	— —	10 5.0	mVdc
Base-Emitter Voltage Differential Gradient (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, T_A = −55 to +125°C)	MD918B,AF MD918A	$\frac{\Delta(V_{BE1}-V_{BE2})}{\Delta T_A}$	— —	— —	20 10	μV/dc °C

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(3) The lowest h_{FE} reading is taken as h_{FE1} for this ratio.

5

FIGURE 1 – DC CURRENT GAIN

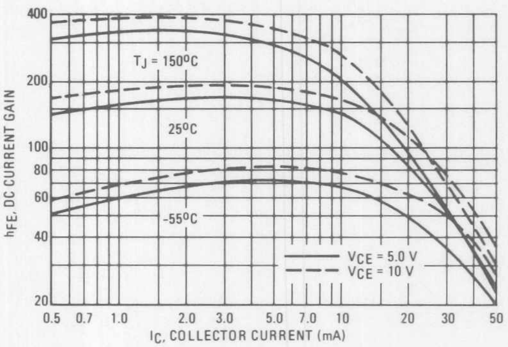


FIGURE 2 – "ON" VOLTAGES

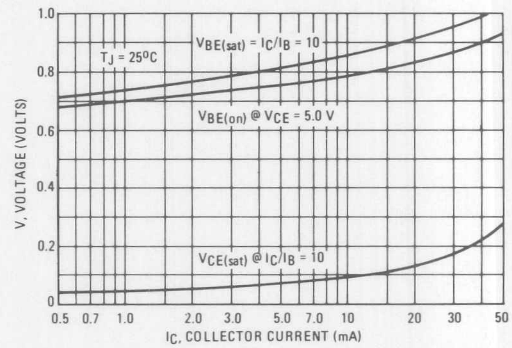


FIGURE 3 – BASE-EMITTER TEMPERATURE COEFFICIENT

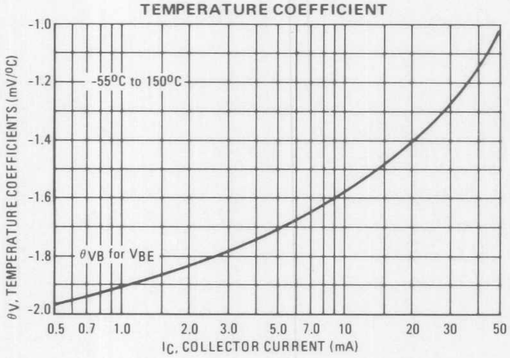
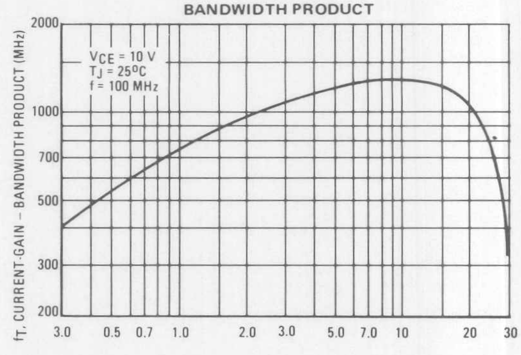
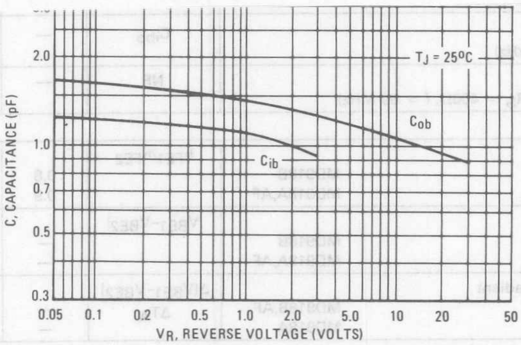


FIGURE 4 – CURRENT-GAIN BANDWIDTH PRODUCT



5

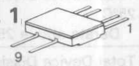


$T_J = 25^oC$
C_{ob}
C_{ib}
C, CAPACITANCE (pF)
2.0
1.0
0.7
0.5
0.3
0.05 0.1 0.2 0.5 1.0 2.0 5.0 10 20 50
V_R, REVERSE VOLTAGE (VOLTS)

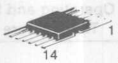
Collector Current — Continuous	I_C	600		mAdc
		One Die	All Die	
Total Device Dissipation @ $T_A = 25°C$	P_D			mW
MD982		600	650	
MD982F		350	400	
MQ982		400	600	
Derate above 25°C				mW/°C
MD982		3.42	3.7	
MD982F		2.0	2.28	
MQ982		2.28	3.42	
Total Device Dissipation @ $T_C = 25°C$	P_D			Watts
MD982		2.1	3.8	
MD982F		1.25	2.5	
MQ982		1.0	4.0	
Derate above 25°C				mW/°C
MD982		12	17.2	
MD982F		7.15	14.3	
MQ982		5.71	22.8	
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

MD982
CASE 654-07, STYLE 1
DUAL

MD982F
CASE 610A-04, STYLE 1
DUAL



MQ982
CASE 607-04, STYLE 1
QUAD



AMPLIFIER TRANSISTOR

PNP SILICON

THERMAL CHARACTERISTICS

Characteristic		Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junction to Case		$R_{\theta JC}$			°C/W
	MD982		83.3	58.3	
	MD982F		140	70	
	MQ982		175	43.8	
Thermal Resistance, Junction to Ambient		$R_{\theta JA}$(1)			°C/W
	MD982		292	270	
	MD982F		500	438	
	MQ982		438	292	
			Junction to Ambient	Junction to Case	
Coupling Factor					%
	MD982		85	40	
	MD982F		75	0	
	MQ982 (Q1-Q2)		57	0	
	(Q1-Q3 or Q1-Q4)		55	0	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

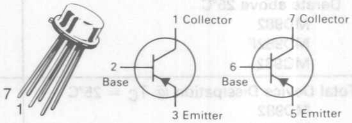
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	50	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$)	I_{CBO}	—	—	0.020	μAdc
($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = 150°C$)		—	—	20	
ON CHARACTERISTICS(2)					
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	20	50	—	—
($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc)		25	75	—	
($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc)		35	90	—	
($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)		40	60	—	
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{CE(sat)}$	—	0.25	0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{BE(sat)}$	—	0.88	1.4	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)	f_T	200	320	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	5.8	8.0	pF
Input Capacitance ($V_{BE} = 2.0$ Vdc, $I_C = 0$, f = 100 kHz)	C_{ibo}	—	16	30	pF

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

5

MD984

CASE 654-07, STYLE 1



DUAL AMPLIFIER TRANSISTOR

PNP SILICON

Refer to MD3250 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value: One Die	Value: Both Die Equal Power	Unit
Collector-Emitter Voltage	V_{CEO}	20		Vdc
Collector-Base Voltage	V_{CBO}	40		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	575 3.29	625 3.57	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.8 10.3	2.5 14.3	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	One Die	Both Die Equal Power	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	97	70	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	304	280	°C/W
		Junction to Ambient	**Junction to Case**	
Coupling Factor		84	44	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

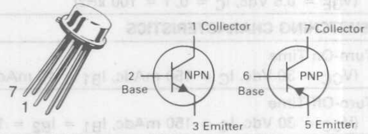
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	20	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0) (V_{CB} = 20 Vdc, I_E = 0, T_A = 150°C)	I_{CBO}	 — —	 — —	 25 30	 nAdc μAdc
ON CHARACTERISTICS					
DC Current Gain(2) (I_C = 10 mAdc, V_{CE} = 10 Vdc)	h_{FE}	25	75	—	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)(2)	$V_{CE(sat)}$	 — —	 0.18 0.38	 0.3 0.5	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{BE(sat)}$	—	0.8	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	250	550	—	MHz

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MD985

CASE 654-07, STYLE 5



COMPLEMENTARY DUAL GENERAL PURPOSE TRANSISTOR

NPN/PNP SILICON

5

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	30		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
		One Die	Both Die Equal Power	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	575 3.29 2.0	625 3.57 2.28	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	 1.8 10.3	 2.5 14.3	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	One Die	Both Die Equal Power	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	97	70	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	304	280	°C/W
		Junction to Ambient	Junction to Case	
Coupling Factors		84	44	%

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

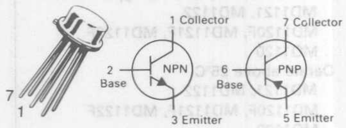
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$) ($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = +150°C$)	I_{CBO}	 — —	 — —	 20 20	 nAdc μAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	 20 25 35 40	 50 75 90 90	 — — — —	—
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{CE(sat)}$	—	0.3	0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{BE(sat)}$	—	1.0	1.4	Vdc

Characteristic	Symbol	Min	Typ	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	200	320	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	5.8	8.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)	C_{ibo}	—	20	—	pF
SWITCHING CHARACTERISTICS					
Turn-On Time (V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_{on}	—	25	—	ns
Turn-Off Time (V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_{off}	—	75	—	ns

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MD986

CASE 654-07, STYLE 5



COMPLEMENTARY DUAL GENERAL PURPOSE TRANSISTOR

NPN/PNP SILICON

5

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	15		Vdc
Collector-Base Voltage	V_{CBO}	40		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
		One Die	Both Die Equal Power	
Total Device Dissipation @ T_A = 25°C	P_D	550	600	mW
Derate above 25°C		3.14	3.42	mW/°C
Total Device Dissipation @ T_C = 25°C	P_D	1.4	2.0	Watts
Derate above 25°C		8.0	11.4	mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	One Die	Both Die Equal Power	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	87.5	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	319	292	°C/W
		Junction to Ambient	Junction to Case	
Coupling Factors		83	40	%

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	15	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0)	I_{CBO}	—	—	25	nAdc
(V_{CB} = 20 Vdc, I_E = 0, T_A = 150°C)		—	—	30	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 10 mAdc, V_{CE} = 10 Vdc)	h_{FE}	25	—	—	—
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$				Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)		—	—	0.3	
(I_C = 50 mAdc, I_B = 10 mAdc)		—	—	0.5	
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{BE(sat)}$	—	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	200	320	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	—	4.0	pF

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

5

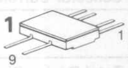
MAXIMUM RATINGS

Rating	Symbol	Value: One Die	Value: All Die Equal Power	Unit
Collector-Emitter Voltage	V_{CEO}	30		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
		One Die	All Die Equal Power	
Total Device Dissipation @ T_A = 25°C	P_D			
MD1121, MD1122		575	625	mW
MD1120F, MD1121F, MD1122F		350	400	
MQ1120		400	600	
Derate above 25°C				
MD1121, MD1122		3.29	3.57	mW/°C
MD1120F, MD1121F, MD1122F		2.0	2.28	
MQ1120		2.28	3.42	
Total Device Dissipation @ T_C = 25°C	P_D			
MD1120, MD1121, MD1122		1.8	2.5	Watts
MD1120F, MD1121F, MD1122F		1.0	2.0	
MQ1120		0.9	3.6	
Derate above 25°C				
MD1120, MD1121, MD1122		10.3	14.3	mW/°C
MD1120F, MD1121F, MD1122F		5.71	11.4	
MQ1120		5.13	20.5	
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

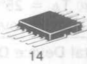
MD1120F
MD1121,F
MD1122,F
MQ1120

MD1121, MD1122
CASE 654-07, STYLE 1

MD1120F
CASE 610A-04, STYLE 1



MQ1120
CASE 607-04, STYLE 1



DUAL
AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MD2218,A for graphs.

THERMAL CHARACTERISTICS

Characteristic	Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$			°C/W
MD1121, MD1122		97	70	
MD1120F, MD1121F, MD1122F		175	87.5	
MQ1120		195	48.8	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)			°C/W
MD1121, MD1122		304	280	
MD1120F, MD1121F, MD1122F		500	438	
MQ1120		438	292	
		Junction to Ambient	Junction to Case	Unit
Coupling Factors				%
MD1121, MD1122		84	44	
MD1120F, MD1121F, MD1122F		75	0	
MQ1120 (Q1-Q2)		57	0	
(Q1-Q3 or Q1-Q4)		55	0	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0)	I_{CBO}	—	—	10	nAdc
(V_{CB} = 50 Vdc, I_E = 0, T_A = 150°C)		—	—	10	μAdc
Emitter Cutoff Current (V_{EB} = 3.0 Vdc, I_C = 0)	I_{EBO}	—	—	10	nAdc

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

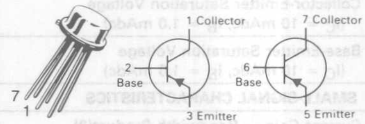
Characteristic		Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS						
DC Current Gain(2)		h_{FE}				—
(I_C = 10 μAdc, V_{CE} = 10 Vdc)			20	40	100	
(I_C = 100 μAdc, V_{CE} = 10 Vdc)			30	50	120	
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)			40	60	160	
(I_C = 10 mAdc, V_{CE} = 10 Vdc)			50	65	200	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{CE(sat)}$	—	80	100	mVdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{BE(sat)}$	—	700	850	mVdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product(2) (I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)		f_T	200	250	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	3.5	8.0	pF
MATCHING CHARACTERISTICS						
DC Current Gain Ratio(3)		h_{FE1}/h_{FE2}				—
(I_C = 100 μAdc, V_{CE} = 10 Vdc)	All Devices		0.8	—	1.0	
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)	MD1122, MD1122F		0.9	—	1.0	
Base-Emitter Voltage Differential		$\|V_{BE1}-V_{BE2}\|$				mVdc
(I_C = 100 μAdc, V_{CE} = 10 Vdc)	All Devices		—	—	10	
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)	MD1122, MD1122F		—	—	5.0	
Base-Emitter Voltage Differential Change Due to Temperature — MD1121, MD1122		$\Delta(V_{BE1}-V_{BE2})$				mVdc
(I_C = 100 μAdc, V_{CE} = 10 Vdc, T_A = −55 to +25°C)			—	—	0.8	
(I_C = 100 μAdc, V_{CE} = 10 Vdc, T_A = +25 to +125°C)			—	—	1.0	

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(3) The lowest h_{FE} reading is taken as h_{FE1} for this ratio.

5

MD1123
MD1130

CASE 654-07, STYLE 1



**DUAL
AMPLIFIER TRANSISTOR**

PNP SILICON

5

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
		One Die	All Die	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	 575 3.29	 625 3.57	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	 1.8 10.3	 2.5 14.3	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	97	70	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	304	280	°C/W
		Junction to Ambient	Junction to Case	
Coupling Factors		84	44	%

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)		$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0) (V_{CB} = 50 Vdc, I_E = 0, T_A = 150°C)		I_{CBO}	 — —	 — —	 10 10	 nAdc μAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)		I_{EBO}	—	—	10	nAdc
ON CHARACTERISTICS						
DC Current Gain(2) (I_C = 10 μAdc, V_{CE} = 10 Vdc)	 MD1130	h_{FE}	 60	 100	 —	—
(I_C = 100 μAdc, V_{CE} = 10 Vdc)	MD1123		30	80	120	
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)	MD1130		100	180	—	
(I_C = 10 mAdc, V_{CE} = 10 Vdc)	MD1123 MD1130		50 100	75 150	200 —	

Characteristic		Symbol	Min	Typ	Max	Unit
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 Adc)		$V_{CE(sat)}$	—	0.18	0.25	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{BE(sat)}$	—	0.8	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product (I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	MD1123 MD1130	f_T	250 200	600 550	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	3.5	4.0	pF
MATCHING CHARACTERISTICS						
DC Current Gain Ratio(3) (I_C = 100 μAdc, V_{CE} = 10 Vdc)	MD1123 MD1130	h_{FE1}/h_{FE2}	0.8 0.9	—	1.0 1.0	—
Base-Emitter Voltage Differential (I_C = 100 μAdc, V_{CE} = 10 Vdc) (I_C = 1.0 mAdc, V_{CE} = 10 Vdc)	MD1123 MD1130	$\|V_{BE1}-V_{BE2}\|$	—	—	10 5.0	mVdc
Base-Emitter Voltage Differential Change Due to Temperature — MD1121, MD1122 (I_C = 100 μAdc, V_{CE} = 10 Vdc, T_A = +25 to +125°C)	MD1130	$\Delta\|V_{BE1}/V_{BE2}\|$	—	—	10	mVdc

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(3) The lowest h_{FE} reading is taken as h_{FE1} for this ratio.

MD1130F For Specifications, See MD1123 Data.

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	15		Vdc
Collector-Base Voltage	V_{CBO}	30		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
		One Die	Both Die	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	550 3.14	600 3.42	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.4 8.0	2.0 11.4	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

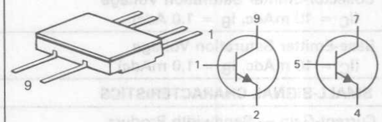
THERMAL CHARACTERISTICS

Characteristic	Symbol	One Die	Both Die Equal Power	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	87.5	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	319	292	°C/W
		Junction to Ambient	Junction to Case	Unit
Coupling Factors		83	40	%

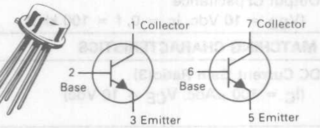
(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

MD1132,F

MD1132F
CASE 610A-04, STYLE 1



MD1132
CASE 654-07, STYLE 1



DUAL
RF AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MD918 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

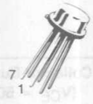
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 3.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	15	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 1.0$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	30	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_E = 0$) ($V_{CB} = 15$ Vdc, $I_E = 0$, $T_A = 150°C$)	I_{CBO}	— —	— —	10 1.0	nAdc μAdc
ON CHARACTERISTICS					
DC Current Gain(2) ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc)	h_{FE}	50	—	—	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	0.2	0.4	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	—	0.7	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	600	800	—	—
Output Capacitance ($V_{CB} = 0$, $I_E = 0$, f = 140 kHz) ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 140 kHz)	C_{obo}	— —	1.5 1.3	3.0 1.7	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 140 kHz)	C_{ibo}	—	1.8	2.0	pF
MATCHING CHARACTERISTICS					
DC Current Gain Ratio(3) ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc)	h_{FE1}/h_{FE2}	0.9	—	1.0	—
Base-Emitter Voltage Differential ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc)	$\lvert V_{BE1}-V_{BE2}\rvert$	—	—	5.0	mVdc
Base-Emitter Voltage Differential Change Due to Temperature ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, $T_A = -55$ to $+25°C$) ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, $T_A = +25$ to $+125°C$)	$\Delta(V_{BE1}-V_{BE2})$	 — —	 — —	 0.8 1.0	mVdc

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(3) The lowest h_{FE} reading is taken as h_{FE1} for this ratio.

MAXIMUM RATINGS

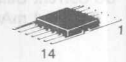
Rating	Symbol	MD2218,A,F MD2219,A,F MQ2218,A MQ2219,A	MD2218AF MD2219AF	Unit
Collector-Emitter Voltage	V_{CEO}	30	40	Vdc
Collector-Base Voltage	V_{CBO}	60	75	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	6.0	Vdc
Collector Current — Continuous	I_C	500		mAdc
		One Die	All Die Equal Power	
Total Device Dissipation @ $T_A = 25°C$	P_D			mW
MD2218,A, MD2219,A		575	625	
MD2218F,AF, MD2219F,AF		350	400	
MQ2218,A, MQ2219,A		400	600	
Derate above 25°C				mW/°C
MD2218,A, MD2219,A		3.29	3.57	
MD2218F,AF, MD2219F,AF		2.0	2.28	
MQ2218,A, MQ2219,A		2.28	3.42	
Total Device Dissipation @ $T_C = 25°C$	P_D			Watts
MD2218,A, MD2219,A		1.8	2.5	
MD2218F,AF, MD2219F,AF		1.0	2.0	
MQ2218,A, MQ2219,A		0.9	3.6	
Derate above 25°C				mW/°C
MD2218,A, MD2219,A		10.3	14.3	
MD2218F,AF, MD2219F,AF		5.71	11.4	
MQ2218,A, MQ2219,A		5.13	20.5	
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

MD2218,A,F,AF
MD2219,A,AF
MQ2218,A
MQ2219,A



MD2218,A
MD2219,A
CASE 654-07, STYLE 1

MD2218F,AF
MD2219,AF
CASE 610A-04, STYLE 1



MQ2218,A
MQ2219,A
CASE 607-04, STYLE 1

DUAL AMPLIFIER TRANSISTOR

NPN SILICON

5

THERMAL CHARACTERISTICS

Characteristic		Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junction to Case		$R_{\theta JC}$			°C/W
	MD2218,A, MD2219,A		97	70	
	MD2218F,AF, MD2219,AF		175	87.5	
	MQ2218,A, MQ2219,A		195	48.8	
Thermal Resistance, Junction to Ambient		$R_{\theta JA}$(1)			°C/W
	MD2218,A, MD2219,A		304	280	
	MD2218,F,AF, MD2219,AF		500	438	
	MQ2218,A, MQ2219,A		438	292	
			Junction to Ambient	Junction to Case	
Coupling Factors					%
	MD2218,A, MD2219,A		84	44	
	MD2218F,AF, MD2219,AF		75	0	
	MQ2218,A, MQ2219,A (Q1-Q2)		57	0	
	(Q1-Q3 or Q1-Q4)		55	0	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$				Vdc
MD2218,A,F, MD2219,A, MQ2218,A, MQ2219,A		30	—		
MD2218AF, MD2219AF		40	—		
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$				Vdc
MD2218,A,F, MD2219,A, MQ2218,A, MD2219,A		60	—	—	
MD2218AF, MD2219AF		75	—	—	

Characteristic		Symbol	Min	Typ	Max	Unit
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$				Vdc
	MD2218,A,F, MD2219,A, MQ2218,A, MQ2219,A		5.0	—	—	
	MD2218AF, MD2219AF		6.0	—	—	
Collector Cutoff Current (V_{CE} = 50 Vdc, $V_{EB(off)}$ = 3.0 Vdc)		I_{CEV}				nAdc
	MD2218,F, MD2219,F, MQ2218,A		20	—	—	
	MD2218A,AF, MD2219A,AF, MQ2219,A		15	—	—	
Base Cutoff Current (V_{CE} = 50 Vdc, $V_{EB(off)}$ = 3.0 Vdc)		I_{BL}	30	—		nAdc
ON CHARACTERISTICS(2)						
DC Current Gain (I_C = 0.1 mAdc, V_{CE} = 10 Vdc)		h_{FE}				—
	MD2218,A,F,AF, MQ2218,A		20	50	—	
	MD2219,A,AF, MQ2219,A		35	45	—	
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)						
	MD2218,A,F,AF, MQ2218,A		25	55	—	
	MD2219,A,AF, MQ2219,A		50	55	—	
(I_C = 10 mAdc, V_{CE} = 10 Vdc)						
	MD2218,A,F,AF, MQ2218,A		35	65	—	
	MD2219,A,AF, MQ2219,A		75	85	—	
(I_C = 150 mAdc, V_{CE} = 1.0 Vdc)						
	MD2218,A,F,AF, MQ2218,A		20	65	—	
	MD2219,A,AF, MQ2219,A		50	65	—	
(I_C = 150 mAdc, V_{CE} = 10 Vdc)						
	MD2218,AF,AF, MQ2218,A		40	30	120	
	MD2219,A,AF, MQ2219,A		100	120	300	
(I_C = 300 mAdc, V_{CE} = 10 Vdc)						
	MD2218,A, MQ2218,A		25	75	—	
	MD2219,A, MQ2219,A		30	75	—	
Collector-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)		$V_{CE(sat)}$				Vdc
	MD2218,A,F, MD2219,A, MQ2218,A, MQ2219,A		—	0.2	0.4	
	MD2218AF, MD2219AF		—	—	0.3	
(I_C = 300 mAdc, I_B = 30 mAdc)						
	MD2218,A,F, MD2219,A, MQ2218,A, MQ2219,A		—	0.35	1.2	
	MD2218AF, MD2219AF		—	—	0.9	
Base-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)		$V_{BE(sat)}$				Vdc
	MD2218,A,F, MD2219,A, MQ2218,A, MQ2219,A		0.6	0.95	1.3	
	MD2218AF, MD2219AF		0.6	1.0	1.2	
(I_C = 300 mAdc, I_B = 30 mAdc)	MD2218,A,F, MD2219,A, MQ2218,A, MQ2219,A		—	—	2.0	
	MD2218AF, MD2219AF		—	—	1.8	
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product (I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)		f_T	200	250		MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	3.5	8.0	pF
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}				pF
	MD2218,A,F, MD2219,A, MQ2218,A, MQ2219,A		—	15	20	
	MD2218AF, MD2219AF		—	18	25	

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS						
Delay Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, $V_{BE(off)}$ = 0.5 Vdc, I_{B1} = 15 mAdc) MD2218,F, MD2219 MD2218A,AF, MD2219A,AF	t_d	— —	— —	20 15	μs
Rise Time	MD2218,F, MD2219 MD2218A,AF, MD2219A,AF	t_r	— —	— —	40 30	μs
Storage Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc) MD2218,F, MD2219 MD2218A,AF, MD2219A,AF	t_s	— —	— —	280 250	μs
Fall Time	MD2218,F, MD2219 MD2218A,AF, MD2219A,AF	t_f	— —	— —	70 60	μs

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 – NORMALIZED DC CURRENT GAIN

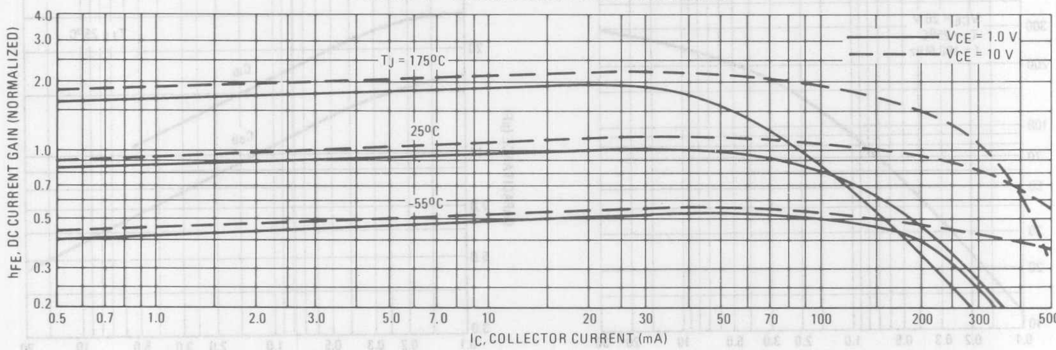


FIGURE 2 – "ON" VOLTAGES

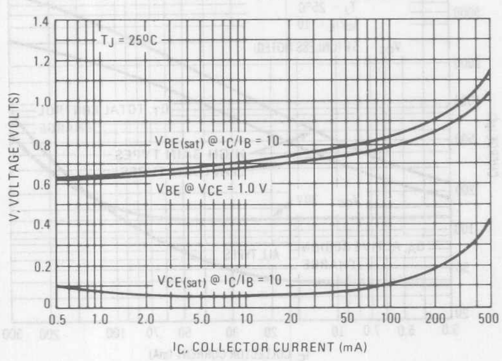
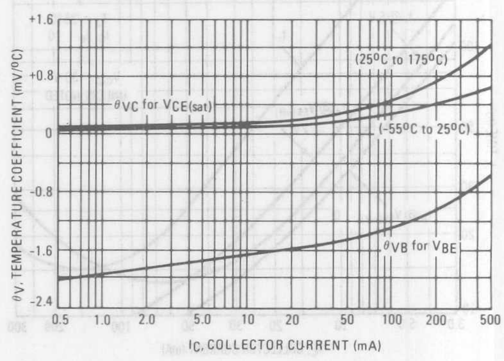


FIGURE 3 – TEMPERATURE COEFFICIENTS



5

NOISE FIGURE
(V_{CE} = 10 Vdc, T_A = 25°C)

FIGURE 4 – FREQUENCY EFFECTS

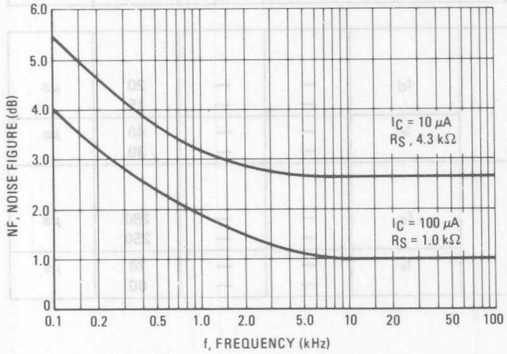


FIGURE 5 – SOURCE RESISTANCE EFFECTS

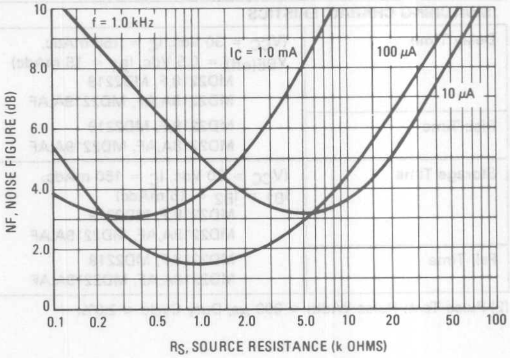


FIGURE 6 – CURRENT-GAIN-BANDWIDTH PRODUCT

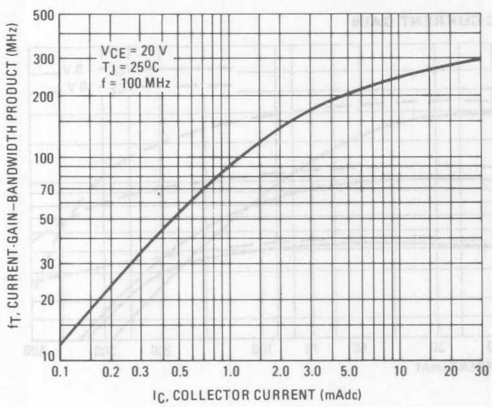
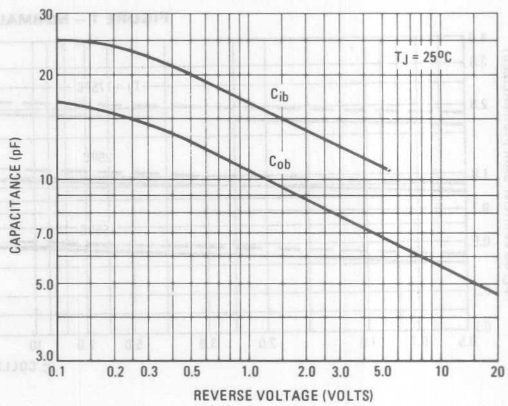


FIGURE 7 – CAPACITANCES



SWITCHING TIME CHARACTERISTICS

FIGURE 8 – TURN-ON TIME

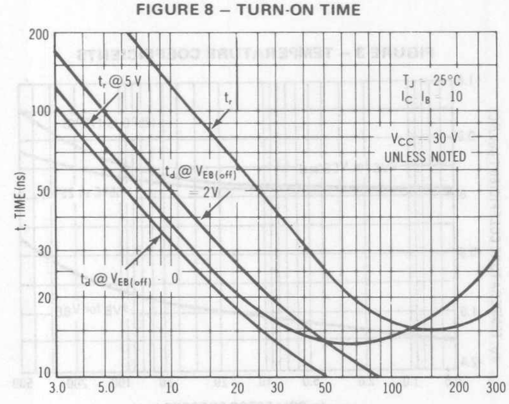


FIGURE 9 – CHARGE DATA

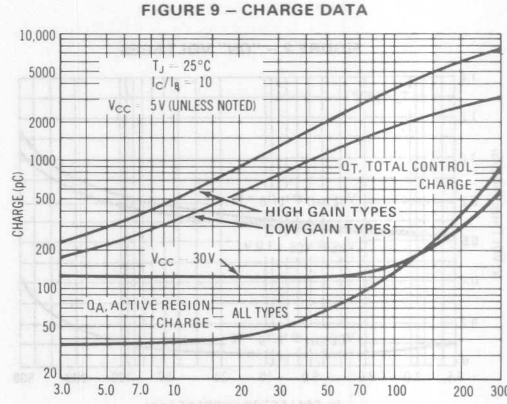


FIGURE 10 – TURN-OFF BEHAVIOR

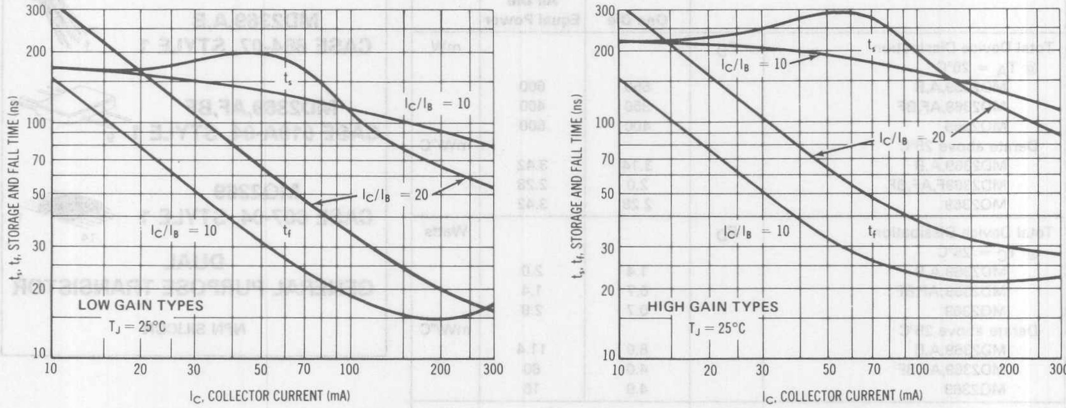


FIGURE 11 – DELAY AND RISE TIME EQUIVALENT TEST CIRCUIT

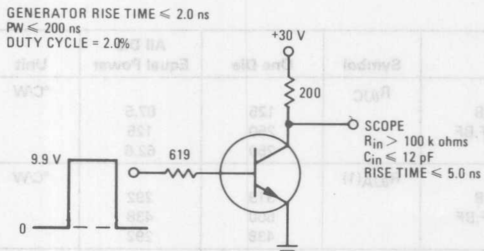
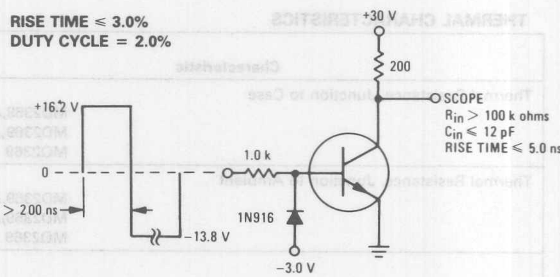


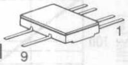
FIGURE 12 – STORAGE TIME AND FALL TIME EQUIVALENT TEST CIRCUIT



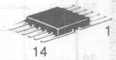
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
		One Die	All Die Equal Power	
Total Device Dissipation @ T_A = 25°C	P_D			mW
MD2369,A,B		550	600	
MD2369,AF,BF		350	400	
MQ2369		400	600	
Derate above 25°C				mW/°C
MD2369,A,B		3.14	3.42	
MD2369F,AF,BF		2.0	2.28	
MQ2369		2.28	3.42	
Total Device Dissipation @ T_C = 25°C	P_D			Watts
MD2369,A,B		1.4	2.0	
MD2369,AF,BF		0.7	1.4	
MQ2369		0.7	2.8	
Derate above 25°C				mW/°C
MD2369,A,B		8.0	11.4	
MD2369,AF,BF		4.0	80	
MQ2369		4.0	16	
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

MQ2369

MD2369,A,B
CASE 654-07, STYLE 1



MD2369,AF,BF
CASE 610A-04, STYLE 1



MQ2369
CASE 607-04, STYLE 1

DUAL
GENERAL PURPOSE TRANSISTOR

NPN SILICON

THERMAL CHARACTERISTICS

Characteristic		Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junction to Case		$R_{\theta JC}$			°C/W
	MD2369,A,B		125	87.5	
	MD2369,AF,BF		250	125	
	MQ2369		250	62.6	
Thermal Resistance, Junction to Ambient		$R_{\theta JA}$(1)			°C/W
	MD2369,A,B		319	292	
	MD2369,AF,BF		500	438	
	MQ2369		438	292	
			Junction to Ambient	Junction to Case	
Coupling Factor	MD2369,A,B		83	40	%
	MD2369,AF,BF		75	0	
	MQ2369 (Q1-Q2)		57	0	
	(Q1-Q3 or Q1-Q4)		55	0	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	15	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current	I_{CBO}				μAdc
(V_{CB} = 20 Vdc, I_E = 0)		—	—	0.03	
(V_{CB} = 20 Vdc, I_E = 0, T_A = +150°C)		—	—	30	
ON CHARACTERISTICS(2)					
DC Current Gain	h_{FE}				—
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)		40	95	140	
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc, T_A = −55°C)		20	—	—	

Characteristic	Symbol	Min	Typ	Max	Unit
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{CE(sat)}$	—	—	0.25	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{BE(sat)}$	0.7	—	0.85	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	500	800	—	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	—	4.0	pF
Input Capacitance (V_{BE} = 1.0 Vdc, I_C = 0, f = 100 MHz)	C_{ibo}	—	—	4.0	pF
SWITCHING CHARACTERISTICS					
Storage Time (V_{CC} = 10 Vdc, I_C = I_{B1} = I_{B2} = 10 mAdc)	t_s	—	—	13	ns
Turn-On Time (V_{CC} = 3.0 Vdc, $V_{BE(off)}$ = 1.5 Vdc, I_C = 10 mAdc, I_{B1} = 3.0 mAdc)	t_{on}	—	—	15	ns
Turn-Off Time (V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = 3.0 mAdc, I_{B2} = 1.5 mAdc)	t_{off}	—	—	20	ns
MATCHING CHARACTERISTICS					
DC Current Gain Ratio(3) (I_C = 3.0 mAdc, V_{CE} = 1.0 Vdc)	h_{FE1}/h_{FE2}				—
MD2369A, MD2369AF		0.9	—	1.0	
MD2369B, MD2369BF		0.8	—	1.0	
Base-Emitter Voltage Differential (I_C = 3.0 mAdc, V_{CE} = 1.0 Vdc)	$\lvert V_{BE1}-V_{BE2}\rvert$				mVdc
MD2369A, MD2369AF		—	—	5.0	
MD2369B, MD2369BF				10	
Base-Emitter Voltage Differential Gradient (I_C = 3.0 mAdc, V_{CE} = 1.0 Vdc, T_A = −55 to +125°C)	$\frac{\Delta(V_{BE1}-V_{BE2})}{\Delta T_A}$				μV/°C
MD2369A, MD2369AF		—	—	10	
MD2369B, MD2369BF		—	—	20	

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(3) The lowest h_{FE} reading is taken as h_{FE1} for this test.

5

FIGURE 1 – STORAGE TIME TEST CIRCUIT

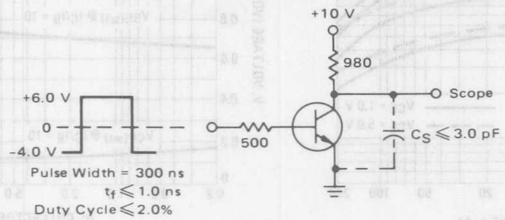


FIGURE 2 – TURN-ON TIME

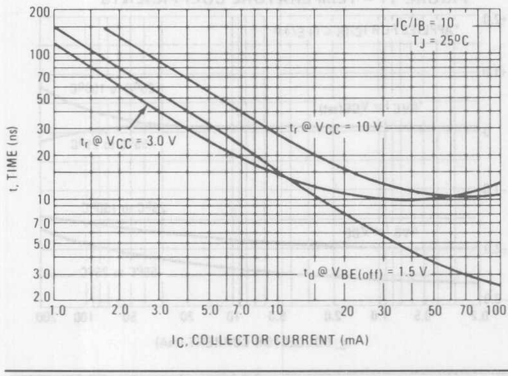
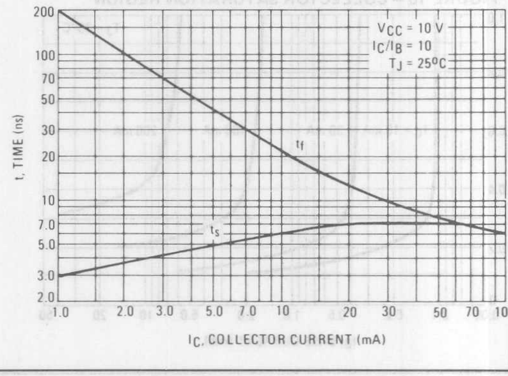


FIGURE 3 – TURN-OFF TIME



5

FIGURE 4 – TURN-ON TEST CIRCUIT

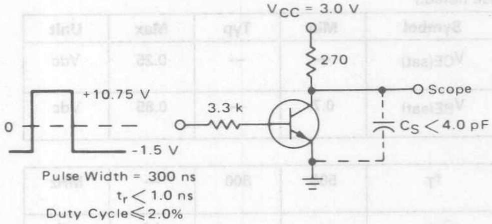


FIGURE 5 – TURN-OFF TEST CIRCUIT

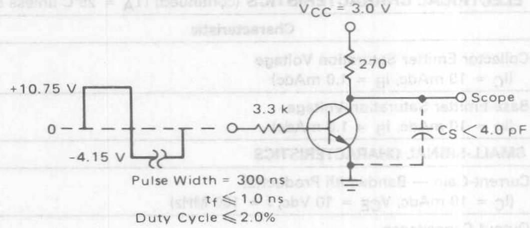


FIGURE 6 – CAPACITANCE

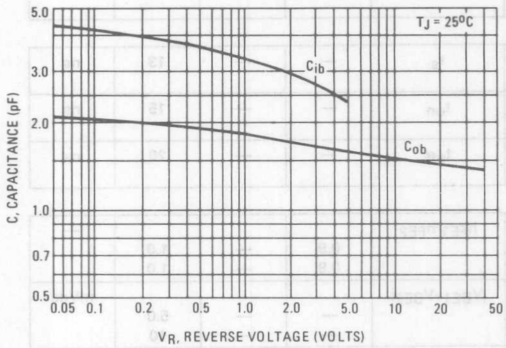


FIGURE 7 – CURRENT-GAIN–BANDWIDTH PRODUCT

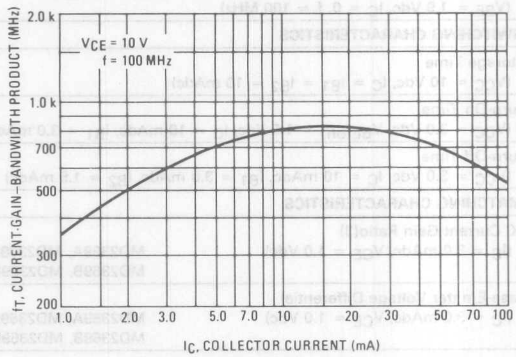


FIGURE 8 – DC CURRENT GAIN

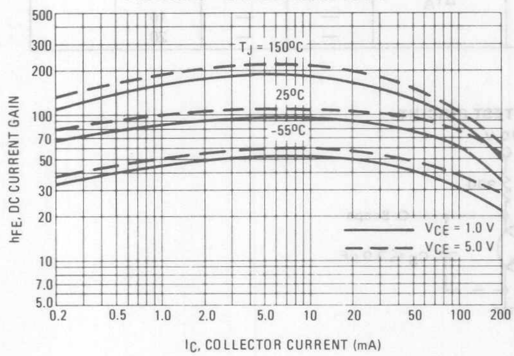


FIGURE 9 – "ON" VOLTAGES

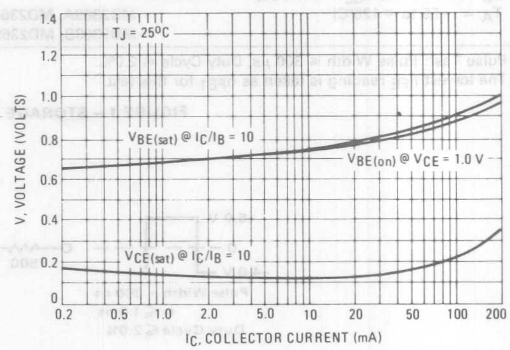


FIGURE 10 – COLLECTOR SATURATION REGION

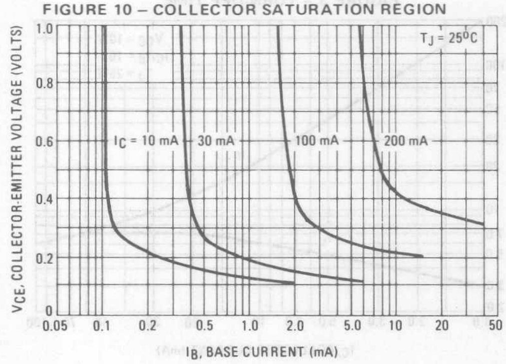
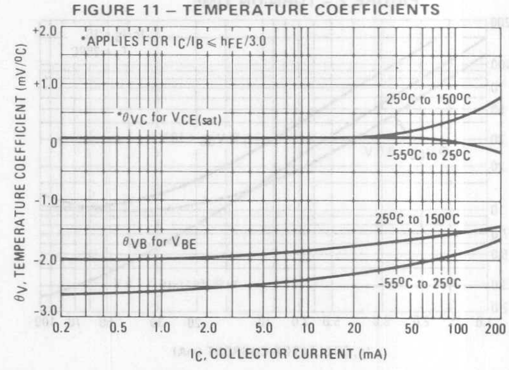


FIGURE 11 – TEMPERATURE COEFFICIENTS



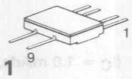
MAXIMUM RATINGS

Rating	Symbol	MD2904,F MD2905,F MQ2904	MD2904A,AF MD2905A,AF MQ2905A	Unit
Collector-Emitter Voltage	V_{CEO}	40	60	Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	600		mAdc
		One Die	All Die Equal Power	
Total Device Dissipation @ $T_A = 25°C$	P_D			mW
MD2904,A, MD2905,A		575	625	
MD2904F,AF, MD2905,AF		350	400	
MQ2904, MQ2905A		400	600	
Derate above 25°C				mW/°C
MD2904,A, MD2905,A		3.29	3.57	
MD2904,F,AF, MD2905,AF		2.0	2.28	
MQ2904, MQ2905A		2.28	3.42	
Total Device Dissipation @ $T_C = 25°C$	P_D			Watts
MD2904,A, MD2905,A		1.8	2.5	
MD2904F,AF, MD2905F,AF		1.0	2.0	
MQ2904, MQ2905A		0.9	3.6	
Derate above 25°C				mW/°C
MD2904,A, MD2905,A		10.3	14.3	
MD2904F,AF, MD2905,AF		5.71	11.4	
MQ2904, MQ2905A		5.13	20.5	
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

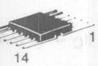
MD2904,A,F,AF
MD2905,A,AF
MQ2904, MQ2905A

MD2904,A
MD2905,A
CASE 654-07, STYLE 1

MD2904F,AF
MD2905,AF
CASE 610A-04, STYLE 1



MQ2904
MQ2905A
CASE 607-04, STYLE 1



DUAL
AMPLIFIER TRANSISTOR
PNP SILICON

5

THERMAL CHARACTERISTICS

Characteristic		Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junction to Case		$R_{\theta JC}$			°C/W
	MD2904,A, MD2905,A		97	70	
	MD2904F,AF, MD2905,AF		175	87.5	
	MQ2904, MQ2905A		195	48.8	
Thermal Resistance, Junction to Ambient		$R_{\theta JA}$(1)			°C/W
	MD2904,A, MD2905,A		304	280	
	MD2904F,AF, MD2905,AF		500	438	
	MQ2904, MQ2905A		438	292	
			Junction to Ambient	Junction to Case	
Coupling Factor					%
	MD2904,A, MD2905,A		84	44	
	MD2904F,AF, MD2905,AF		75	0	
	MQ2904, MQ2905A (Q1-Q2)		57	0	
	(Q1-Q3 or Q1-Q4)		55	0	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$				Vdc
	MD2904, MD2905		40	—	—	
	MD2904A, MD2905A		60	—	—	
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)		$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current		I_{CBO}				μAdc
($V_{CB} = 50$ Vdc, $I_E = 0$)			—	—	0.020	
($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = 150°C$)			—	—	30	

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)		I_{EBO}	—	—	30	nAdc
ON CHARACTERISTICS(2)						
DC Current Gain		h_{FE}				—
(I_C = 0.1 mAdc, V_{CE} = 10 Vdc)	MD2904		20	50	—	
	MD2904A		40	70	—	
	MD2905		35	70	—	
	MD2905A		75	150	—	
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)	MD2904		25	75	—	
	MD2904A		40	75	—	
	MD2905		50	100	—	
	MD2905A		100	175	—	
(I_C = 10 mAdc, V_{CE} = 10 Vdc)	MD2904		35	90	—	
	MD2904A		40	90	—	
	MD2905		75	110	—	
	MD2905A		100	200	—	
(I_C = 150 mAdc, V_{CE} = 10 Vdc)	MD2904,A,		40	90	120	
	MD2905,A		100	200	300	
(I_C = 500 mAdc, V_{CE} = 10 Vdc)	MD2904		20	60	—	
	MD2904A		40	80	—	
	MD2905		30	130	—	
	MD2905A		50	150	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$				Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)			—	0.25	0.4	
(I_C = 500 mAdc, I_B = 50 mAdc)			—	0.5	1.6	
Base-Emitter Saturation Voltage		$V_{BE(sat)}$				Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)			—	0.88	1.3	
(I_C = 500 mAdc, I_B = 50 mAdc)			—	1.0	2.6	
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product(3) (I_C = 50 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)		f_T	200	320	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	5.8	8.0	pF
Input Capacitance (V_{BE} = 2.0 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	16	30	pF
SWITCHING CHARACTERISTICS						
Turn-On Time	(V_{CC} = 30 Vdc, V_{BE} = 0.5 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_{on}	—	—	45	ns
Delay Time		t_d	—	—	12	ns
Rise Time		t_r	—	—	35	ns
Turn-Off Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_{off}	—	—	130	ns
Storage Time		t_s	—	—	100	ns
Fall Time		t_f	—	—	40	ns

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(3) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

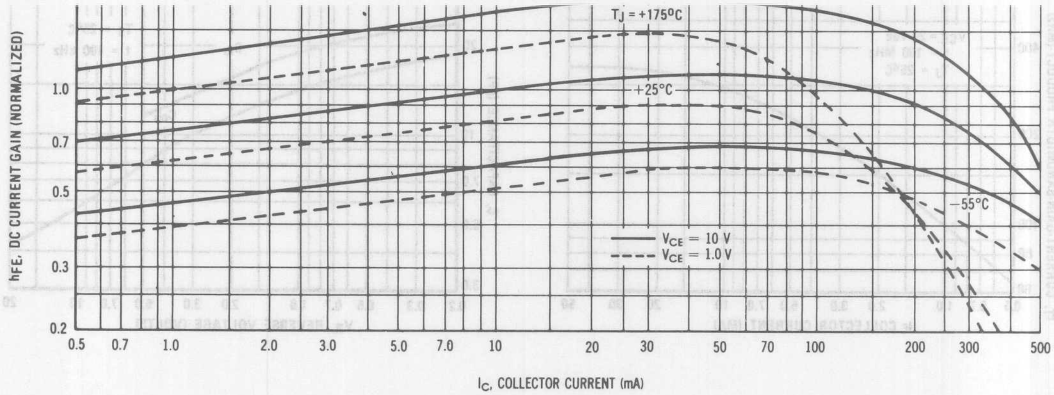


FIGURE 2 — "ON" VOLTAGES

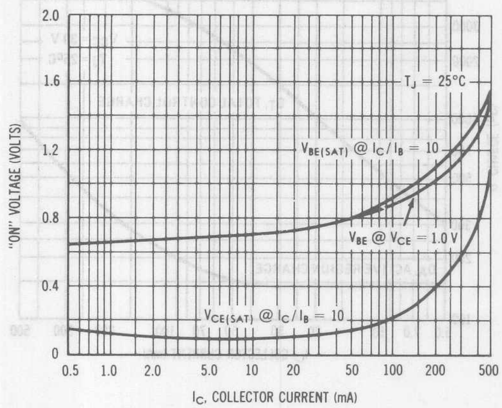
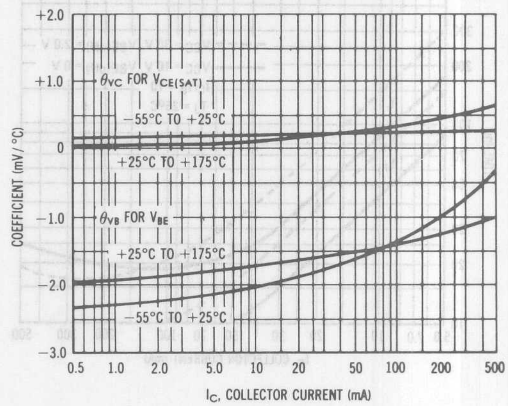


FIGURE 3 — TEMPERATURE COEFFICIENTS



NOISE FIGURE

$V_{CE} = 10\ V$, $T_A = 25^oC$

FIGURE 4 — FREQUENCY EFFECTS

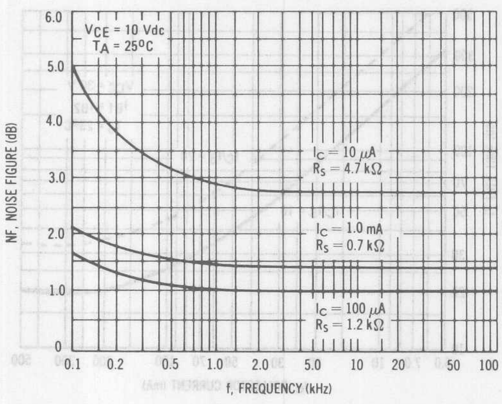


FIGURE 5 — SOURCE RESISTANCE EFFECTS

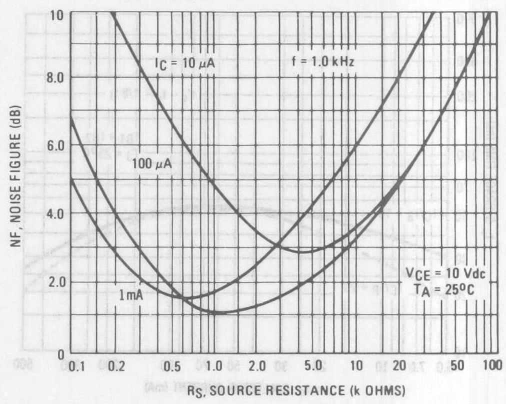


FIGURE 6 – CURRENT-GAIN BANDWIDTH PRODUCT

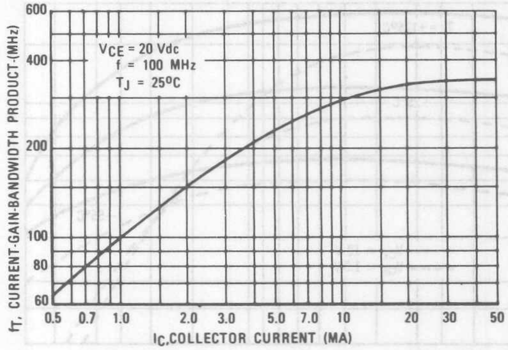


FIGURE 7 – CAPACITANCE

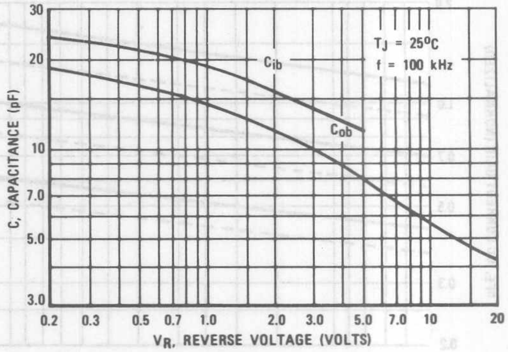


FIGURE 8 – TURN ON TIME

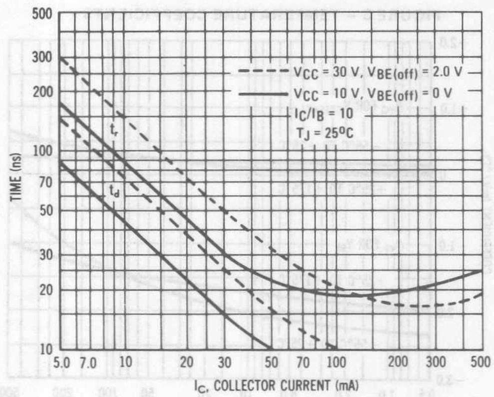


FIGURE 9 – CHARGE DATA

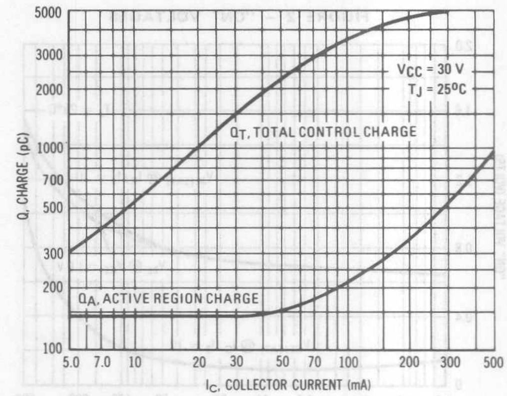


FIGURE 10 – STORAGE TIME

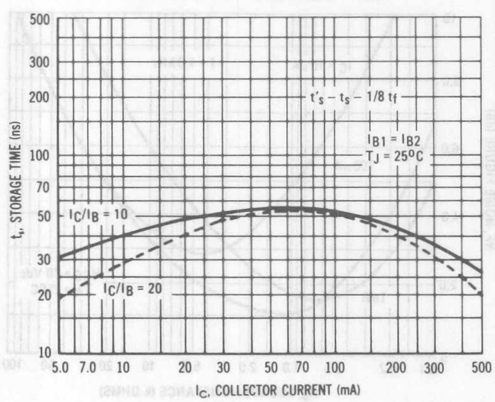


FIGURE 11 – FALL TIME

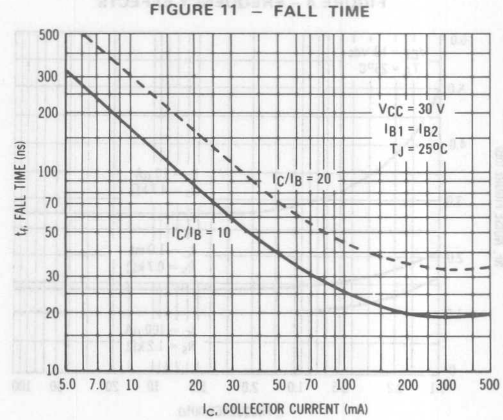


FIGURE 12 – DELAY AND RISE TIME TEST CIRCUIT

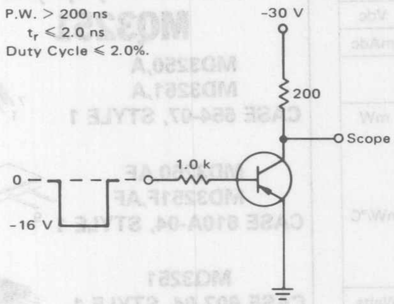
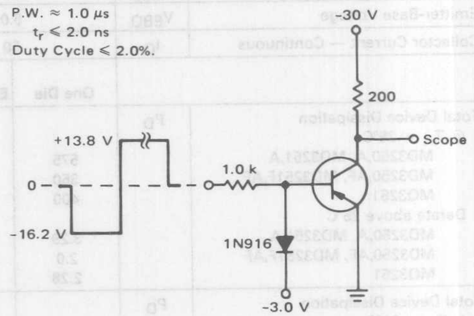


FIGURE 13 – STORAGE AND FALL TIME TEST CIRCUIT

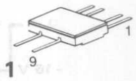


5

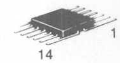
MD3251,A,F,AF
MQ3251

MD3250,A
MD3251,A
CASE 654-07, STYLE 1

MD3250,AF
MD3251F,AF
CASE 610A-04, STYLE 1



MQ3251
CASE 607-04, STYLE 1



DUAL AMPLIFIER TRANSISTOR

PNP SILICON

Collector-Base Voltage	V_{CBO}	50		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
		One Die	All Die Equal Power	
Total Device Dissipation @ $T_A = 25°C$	P_D			mW
MD3250,A, MD3251,A		575	625	
MD3250,AF, MD3251F,AF		350	400	
MQ3251		400	600	
Derate above 25°C				mW/°C
MD3250,A, MD3251,A		3.29	3.57	
MD3250,AF, MD3251F,AF		2.0	2.28	
MQ3251		2.28	3.42	
Total Device Dissipation @ $T_C = 25°C$	P_D			Watts
MD3250,A, MD3251,A		1.8	2.5	
MD3250,AF, MD3251F,AF		1.0	2.0	
MQ3251		0.9	3.6	
Derate above 25°C				mW/°C
MD3250,A, MD3251,A		10.3	14.3	
MD3250,AF, MD3251F,AF		5.71	11.4	
MQ3251		5.13	20.5	
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic		Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junctioh to Case		$R_{\theta JC}$			°C/W
	MD3251,A, MD3251,A		97	70	
	MD3250,AF, MD3251F,AF		175	87.5	
	MQ3251		195	48.8	
Thermal Resistance, Junction to Ambient		$R_{\theta JA}$(1)			°C/W
	MD3250,A, MD3251,A		304	280	
	MD3250,AF, MD3251F,AF		500	438	
	MQ3251		438	292	
			Junction to Ambient	Junction to Case	
Coupling Factors					%
	MD3250,A, MD3251,A		84	44	
	MD3250,AF, MD3251F,AF		75	0	
	MQ3251 (Q1-Q2)		57	0	
	(Q1-Q3 or Q1-Q4)		55	0	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	50	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current	I_{CBO}				
($V_{CB} = 40$ Vdc, $I_E = 0$)		—	—	10	nAdc
($V_{CB} = 40$ Vdc, $I_E = 0$, $T_A = 150°C$)		—	—	10	μAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	10	nAdc

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS(2)						
DC Current Gain		h_{FE}				—
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc)	MD3250,A,AF		25	75	—	
	MD3251,A,F,AF		50	100	—	
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	MD3250,A,AF		50	82	150	
	MD3251,A,F,AF		80	170	300	
	MQ3251		80	170	—	
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc, T_A = −55°C)	MD3250,A,AF		25	35	—	
	MD3251,A,F,AF		50	75	—	
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	MD3250,A,AF		50	87	150	
	MD3251,A,F,AF		100	180	300	
	MQ3251		100	180	—	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	MD3250,A,AF		50	92	—	
	MD3251,A,F,AF		100	190	—	
	MQ3251		100	190	300	
(I_C = 50 mAdc, V_{CE} = 5.0 Vdc)	MD3250,A,AF		15	50	—	
	MD3251,A,F,AF		30	90	—	
	MQ3251		30	90	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$				Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)			—	0.11	0.25	
(I_C = 50 mAdc, I_B = 5.0 mAdc)			—	0.18	0.5	
Base-Emitter Saturation Voltage		$V_{BE(sat)}$				Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)			0.6	0.78	0.9	
(I_C = 50 mAdc, I_B = 5.0 mAdc)			—	0.88	1.2	
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product		f_T				MHz
(I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	MD3250,A,AF		200	600	—	
	MD3251,A,F,AF		250	600	—	
	MQ3251		300	600	—	
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	2.5	6.0	pF
Input Capacitance (V_{BE} = 1.0 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	6.0	8.0	pF
MATCHING CHARACTERISTICS (MD3250,A,AF & MD3251,A,F,AF ONLY)						
DC Current Gain Ratio(3)		h_{FE1}/h_{FE2}				—
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc)			0.9	—	1.0	
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)			0.9	—	1.0	
Base-Emitter Voltage Differential		$\|V_{BE1}-V_{BE2}\|$				mVdc
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc)			—	—	3.0	
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc)			—	—	5.0	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)			—	—	5.0	
Base-Emitter Voltage Differential Change Due to Temperature		$\Delta\|V_{BE1}/V_{BE2}\|$				mVdc
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc, T_A = −55 to +25°C)			—	—	0.8	
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc, T_A = +25 to +125°C)			—	—	1.0	

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(3) The lowest h_{FE} reading is taken as h_{FE1} for this ratio.

5

FIGURE 1 – CAPACITANCE

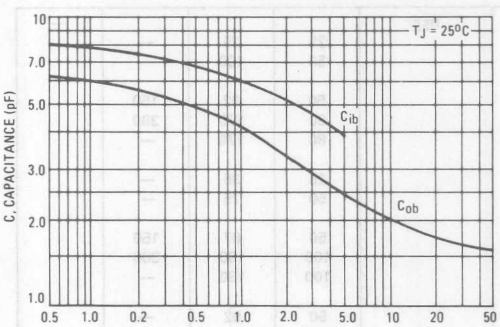
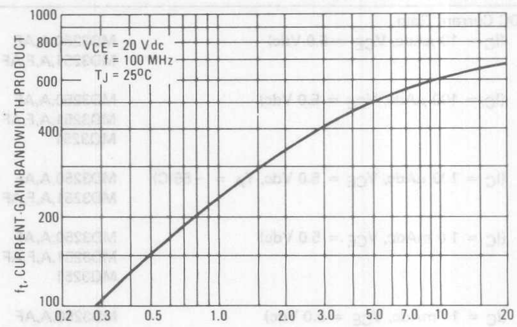


FIGURE 2 – CURRENT-GAIN BANDWIDTH PRODUCT



NOISE FIGURE VARIATIONS

(V_{CE} = 6.0 V, T_A = 25°C)

FIGURE 3 – EFFECTS OF FREQUENCY

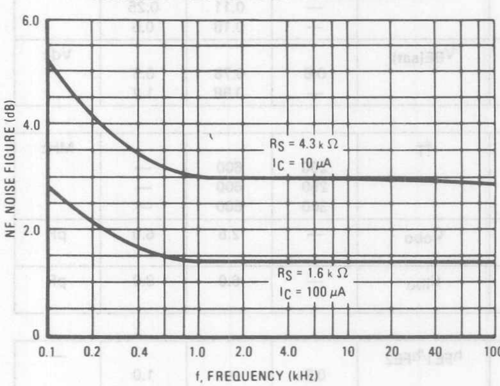


FIGURE 4 – EFFECTS OF SOURCE RESISTANCE

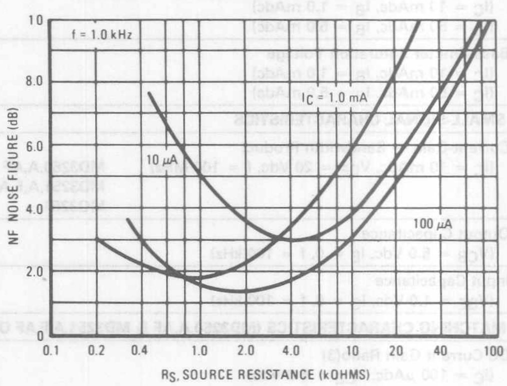


FIGURE 5 – DC CURRENT GAIN

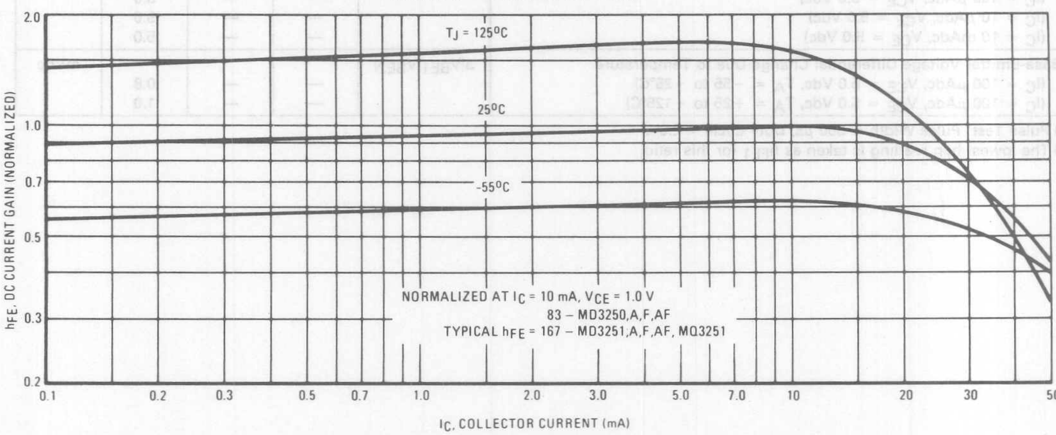


FIGURE 6 – "ON" VOLTAGE

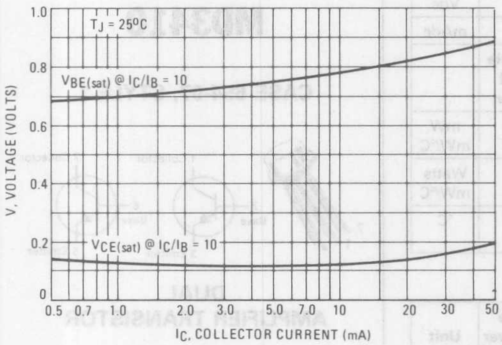


FIGURE 7 – TEMPERATURE COEFFICIENTS

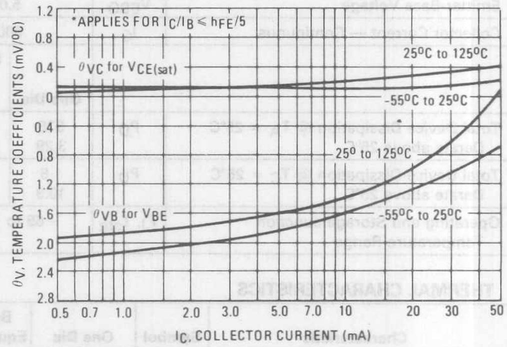
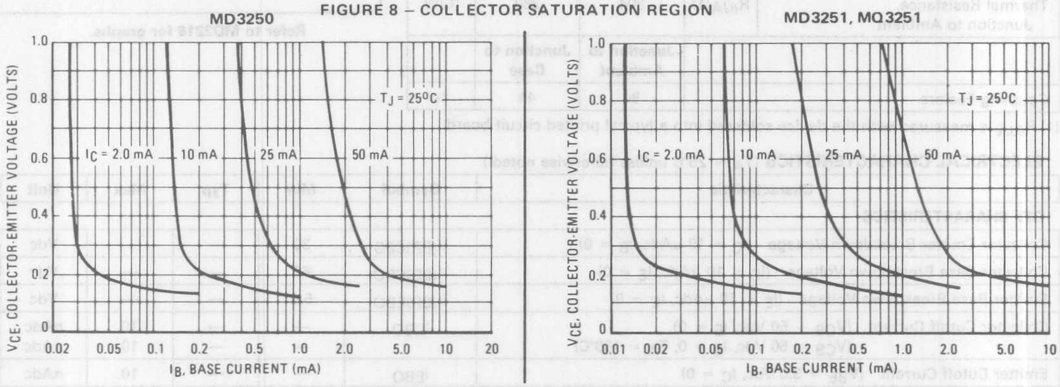
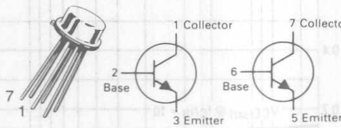


FIGURE 8 – COLLECTOR SATURATION REGION



MD3409
MD3410

CASE 654-07, STYLE 1



DUAL AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MD2218 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	30		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
		One Die	Both Die Equal Power	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	575 3.29	625 3.57	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.8 10.3	2.5 14.3	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	One Die	Both Die Equal Power	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	97	70	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	304	280	°C/W
		Junction to Ambient	Junction to Case	
Coupling Factors		84	44	%

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage ($I_C = 10\ \mu Adc$, $I_B = 0$)		$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu Adc$, $I_E = 0$)		$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu Adc$, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$) ($V_{CB} = 50$ Vdc, $I_E = 0$, $T_A = 150°C$)		I_{CBO}	— —	— —	10 10	nAdc μAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)		I_{EBO}	—	—	10	nAdc
ON CHARACTERISTICS						
DC Current Gain(2)		h_{FE}				—
($I_C = 10\ \mu Adc$, $V_{CE} = 10$ Vdc)	MD3410		20	40	100	
($I_C = 100\ \mu Adc$, $V_{CE} = 10$ Vdc)	Both Devices		30	50	120	
($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc)	Both Devices		40	60	160	
($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc)	Both Devices		50	65	200	
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)		$V_{CE(sat)}$	—	0.09	0.15	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)		$V_{BE(sat)}$	—	0.7	0.85	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product ($I_C = 20$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)		f_T	200	250	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{obo}	—	3.5	8.0	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)		C_{ibo}	—	15	25	pF
MATCHING CHARACTERISTICS						
Base-Emitter Voltage Differential Change Due to Temperature		$\lvert V_{BE1}-V_{BE2}\rvert$				mVdc
($I_C = 100\ \mu Adc$, $V_{CE} = 10$ Vdc,	MD3409		—	—	1.6	
$T_A = -55°C$ to $+25°C$)	MD3410		—	—	0.8	
($I_C = 100\ \mu Adc$, $V_{CE} = 10$ Vdc,	MD3409		—	—	2.0	
$T_A = +25°C$ to $+125°C$)	MD3410		—	—	1.0	

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

Collector-Base Voltage	V_{CBO}	40		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	1.5		Adc
		One Die	All Die Equal Power	
Total Device Dissipation @ $T_A = 25°C$	P_D			mW
MD3467		600	650	
MQ3467		400	600	
Derate above 25°C				mW/°C
MD3467		3.42	3.7	
MQ3467		2.28	3.42	
Total Device Dissipation @ $T_C = 25°C$	P_D			Watts
MD3467		2.1	3.0	
MQ3467		1.0	4.0	
Derate above 25°C				mW/°C
MD3467		12	17.2	
MQ3467		5.71	22.8	
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

MD3467
MQ3467

MD3467
CASE 654-07, STYLE 1

MQ3467
CASE 607-04, STYLE 1

DUAL
AMPLIFIER TRANSISTOR

PNP SILICON

THERMAL CHARACTERISTICS

Characteristic	Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$			°C/W
MD3467		83.3	58.3	
MQ3467		175	43.8	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)			°C/W
MD3467		292	270	
MQ3467		438	292	
		Junction to Ambient	Junction to Case	
Coupling Factors				%
MD3467		85	40	
MQ3467 (Q1-Q2)		57	0	
(Q1-Q3 or Q1-Q4)		55	0	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$, $T_A = 100°C$)	I_{CBO}	—	—	10	μAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	100	nAdc

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS						
DC Current Gain (I_C = 500 mAdc, V_{CE} = 1.0 Vdc)		h_{FE}	20	—	—	—
Collector-Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc)		$V_{CE(sat)}$	—	0.32	0.5	Vdc
Base-Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc)		$V_{BE(sat)}$	—	0.95	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	150	220	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 140 kHz)		C_{obo}	—	8.5	20	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 140 kHz)		C_{ibo}	—	22	80	pF
SWITCHING CHARACTERISTICS						
Delay Time	(V_{CC} = 30 Vdc, V_{BE} = 2.0 Vdc, I_C = 500 mAdc, I_{B1} = 50 mAdc)	t_d	—	7.0	10	ns
Rise Time		t_r	—	17	30	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 500 mAdc, I_{B1} = I_{B2} = 50 mAdc)	t_s	—	58	80	ns
Fall Time		t_f	—	14	30	ns

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

5

FIGURE 1 – DC CURRENT GAIN

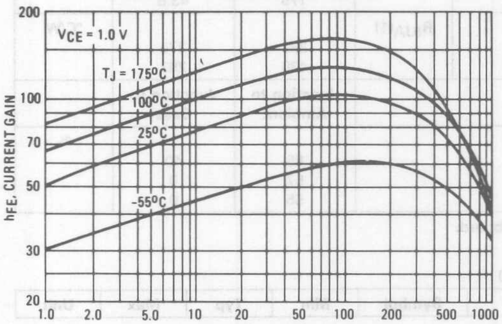


FIGURE 2 – COLLECTOR SATURATION REGION

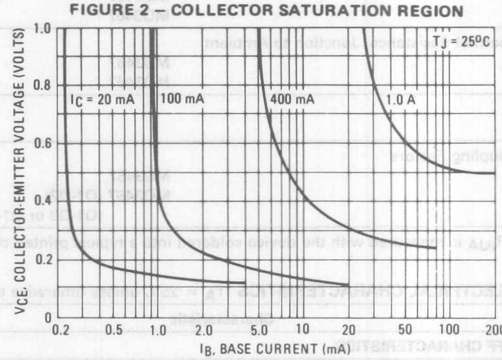


FIGURE 3 – "ON" VOLTAGE

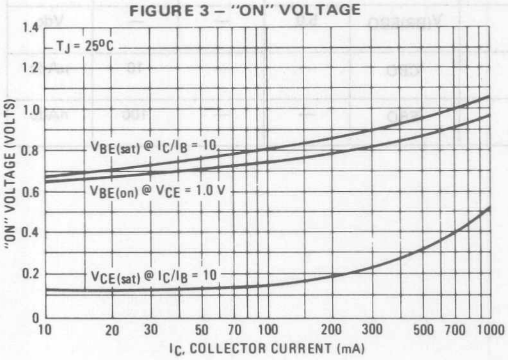


FIGURE 4 – TEMPERATURE COEFFICIENTS

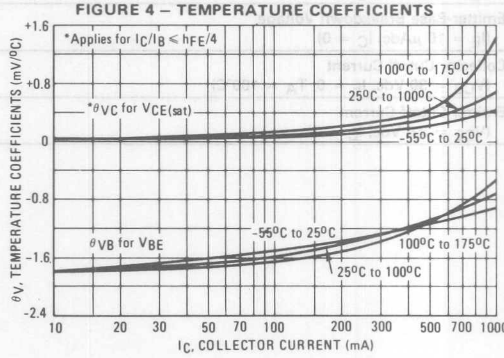


FIGURE 5 – ACTIVE REGION SAFE OPERATING AREA

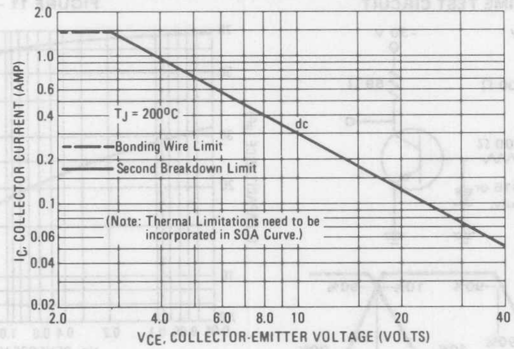


FIGURE 6 – TURN-ON TIME

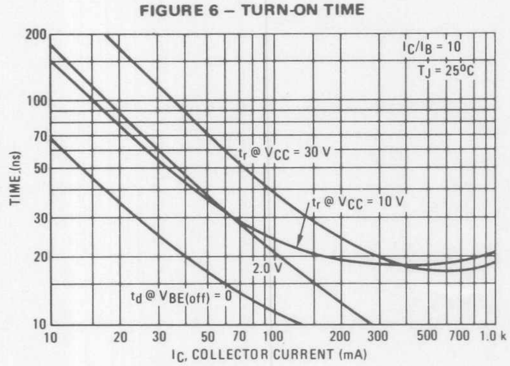


FIGURE 7 – RISE AND FALL TIME

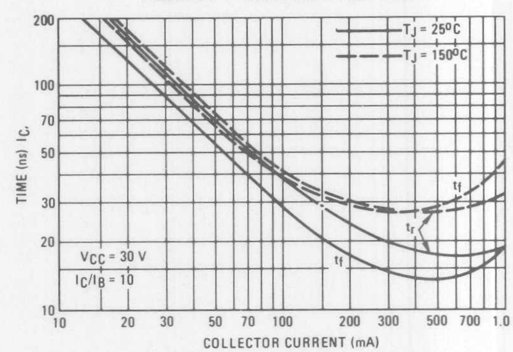


FIGURE 8 – STORAGE TIME

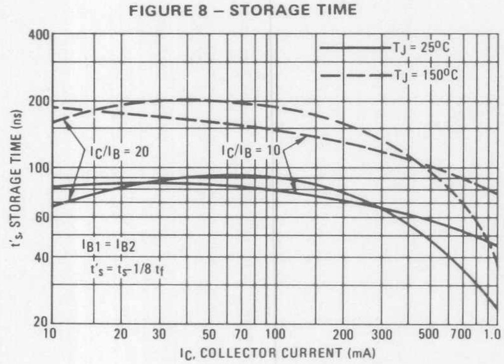
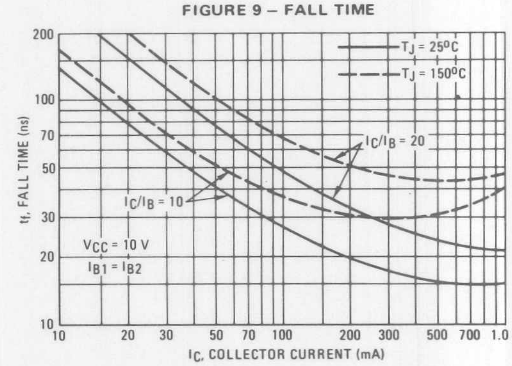
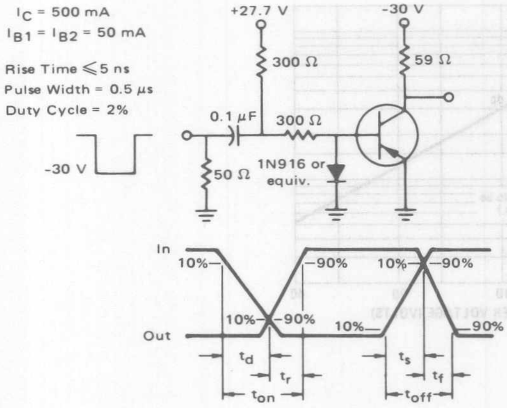
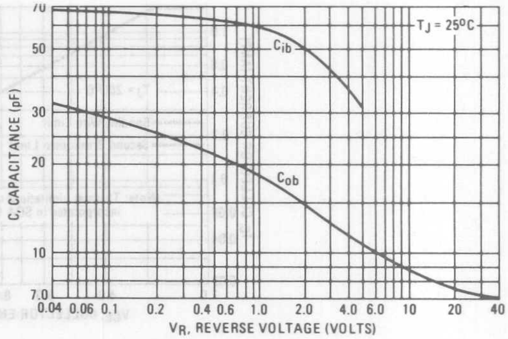


FIGURE 9 – FALL TIME





I_C = 500 mA
I_{B1} = I_{B2} = 50 mA
Rise Time ≤ 5 ns
Pulse Width = 0.5 μs
Duty Cycle = 2%
-30 V
+27.7 V
-30 V
300 Ω
59 Ω
0.1 μF
300 Ω
50 Ω
1N916 or equiv.
In
10%
90%
10%
90%
Out
10%
90%
10%
90%
t_d
t_r
t_{on}
t_s
t_f
t_{off}



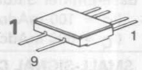
T_J = 25°C
C_{ib}
C_{ob}
C, CAPACITANCE (pF)
70
50
30
20
10
7.0
0.04 0.06 0.1 0.2 0.4 0.6 1.0 2.0 4.0 6.0 10 20 40
V_R, REVERSE VOLTAGE (VOLTS)

5

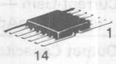
Rating	Symbol	One Die	All Die Equal Power	Unit
Collector-Base Voltage	V_{CBO}	65		Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	1.0		Adc
		One Die	All Die Equal Power	
Total Device Dissipation @ $T_A = 25°C$	P_D			mW
MD3725		600	650	
MD3725F		350	400	
MQ3725		400	600	
Derate above 25°C				mW/°C
MD3725		3.42	3.7	
MD3725F		2.0	2.28	
MQ3725		2.28	3.42	
Total Device Dissipation @ $T_C = 25°C$	P_D			Watts
MD3725		2.1	3.0	
MD3725F		1.25	2.5	
MQ3725		1.0	4.0	
Derate above 25°C				mW/°C
MD3725		12	17.2	
MD3725F		7.15	14.3	
MQ3725		5.71	22.8	
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

MQ3725

MD3725
CASE 654-07, STYLE 1



MD3725F
CASE 610A-04, STYLE 1



MQ3725
CASE 607-04, STYLE 1

DUAL
AMPLIFIER TRANSISTOR

NPN SILICON

5

THERMAL CHARACTERISTICS

Characteristic		Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junction to Case		$R_{\theta JC}$			°C/W
	MD3725		83.3	58.3	
	MD3725F		140	70	
	MQ3725		175	43.8	
Thermal Resistance, Junction to Ambient		$R_{\theta JA}$(1)			°C/W
	MD3725		292	270	
	MD3725F		500	438	
	MQ3725		433	292	
			Junction to Ambient	Junction to Case	
Coupling Factor					%
	MD3725		85	40	
	MD3725F		75	0	
	MQ3725 (Q1-Q2)		57	0	
	(Q1-Q3, Q1-Q4)		55	0	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 10\ \mu$Adc, $V_{BE} = 0$)	MD3725F	$V_{(BR)CES}$	65	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)		$V_{(BR)CBO}$	65	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	6.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 40$ Vdc, $I_E = 0$)		I_{CBO}	—	0.12	1.7	μAdc
($V_{CB} = 40$ Vdc, $I_E = 0$, $T_A = 100°C$)			—	—	120	μAdc

5

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS(2)					
DC Current Gain (I_C = 100 mAdc, V_{CE} = 1.0 Vdc)	h_{FE}	50	—	150	—
(I_C = 500 mAdc, V_{CE} = 2.0 Vdc)		30	—	—	
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 10 mAdc)	$V_{CE(sat)}$	—	0.19	0.26	Vdc
(I_C = 500 mAdc, I_B = 50 mAdc)		—	0.30	0.45	
Base-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 10 mAdc)	$V_{BE(sat)}$	—	—	0.86	Vdc
(I_C = 500 mAdc, I_B = 50 mAdc)		0.80	—	1.2	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	200	—	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	—	10	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)	C_{ibo}	—	—	65	pF
SWITCHING CHARACTERISTICS					
Turn-On Time (V_{CC} = 30 Vdc, I_C = 500 mAdc, I_{B1} = 50 mAdc, $V_{BE(off)}$ = 3.8 Vdc)	t_{on}	—	20	45	ns
Turn-Off Time (V_{CC} = 30 Vdc, I_C = 500 mAdc, I_{B1} = I_{B2} = 50 mAdc)	t_{off}	—	50	75	ns

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

TYPICAL DC CHARACTERISTICS

FIGURE 1 – DC CURRENT GAIN

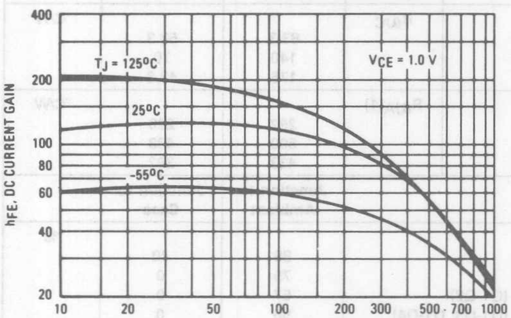


FIGURE 2 – "ON" VOLTAGES

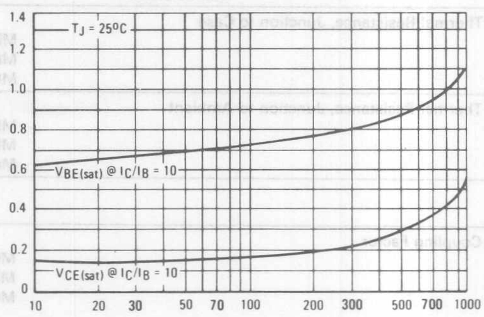


FIGURE 3 – COLLECTOR SATURATION REGION

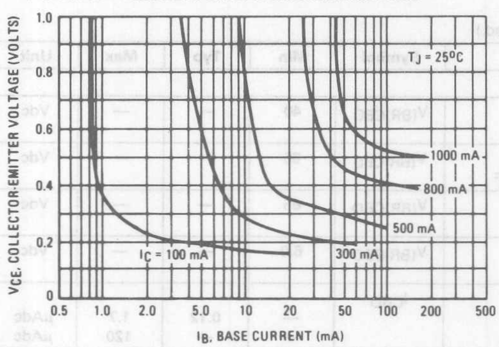
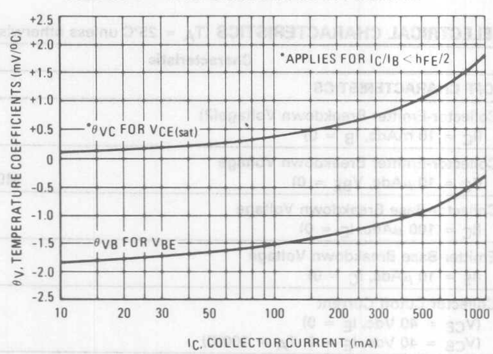


FIGURE 4 – TEMPERATURE COEFFICIENTS



TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 5 – CURRENT-GAIN – BANDWIDTH PRODUCT

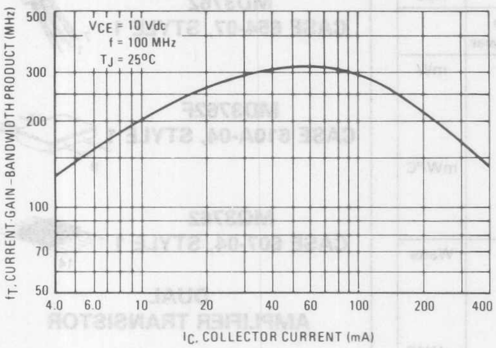


FIGURE 6 – CAPACITANCE

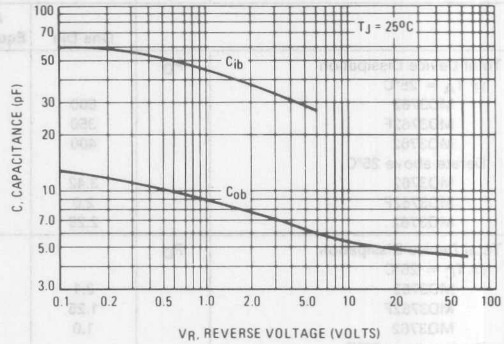


FIGURE 7 – TURN-ON TIME

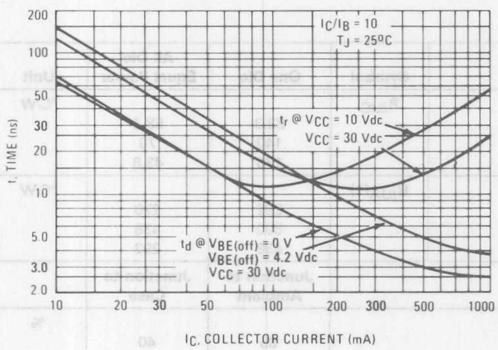


FIGURE 8 – TURN-OFF TIME

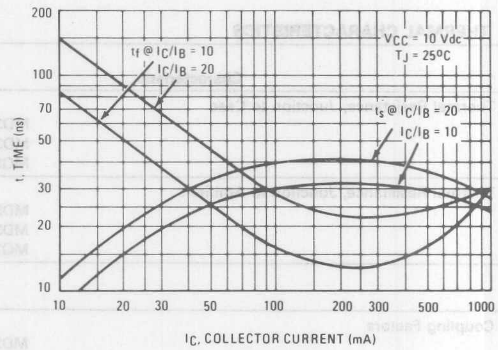


FIGURE 9 – SWITCHING TIME TEST CIRCUIT

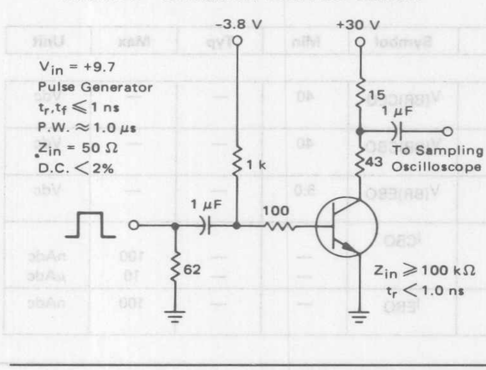
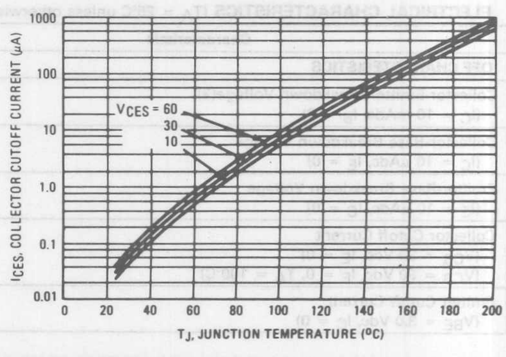


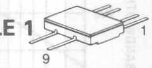
FIGURE 10 – COLLECTOR CUTOFF CURRENT



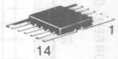
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	1.5		Adc
		One Die	All Die Equal Power	
Total Device Dissipation @ $T_A = 25°C$	P_D			mW
MD3762		600	650	
MD3762F		350	400	
MQ3762		400	600	
Derate above 25°C				mW/°C
MD3762		3.42	3.7	
MD3762F		2.0	2.28	
MQ3762		2.28	3.42	
Total Device Dissipation @ $T_C = 25°C$	P_D			Watts
MD3762		2.1	3.0	
MD3762F		1.25	2.5	
MQ3762		1.0	4.0	
Derate above 25°C				mW/°C
MD3762		12	17.2	
MD3762F		7.15	14.3	
MQ3762		5.71	22.8	
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

MD3762
CASE 654-07, STYLE 1

MD3762F
CASE 610A-04, STYLE 1



MQ3762
CASE 607-04, STYLE 1



DUAL AMPLIFIER TRANSISTOR

PNP SILICON

5

THERMAL CHARACTERISTICS

Characteristic		Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junction to Case		$R_{\theta JC}$			°C/W
	MD3762		83.3	58.3	
	MD3762F		140	70	
	MQ3762		175	43.8	
Thermal Resistance, Junction to Ambient		$R_{\theta JA}$(1)			°C/W
	MD3762		292	270	
	MD3762F		500	438	
	MQ3762		438	292	
			Junction to Ambient	Junction to Case	
Coupling Factors					%
	MD3762		85	40	
	MD3762F		75	0	
	MQ3762 (Q1-Q2)		57	0	
	(Q1-Q3, Q1-Q4)		55	0	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current	I_{CBO}				
($V_{CB} = 30$ Vdc, $I_E = 0$)		—	—	100	nAdc
($V_{CB} = 30$ Vdc, $I_E = 0$, $T_A = 100°C$)		—	—	10	μAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	100	nAdc

Characteristic		Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS(2)						
DC Current Gain (I_C = 1.0 Adc, V_{CE} = 2.0 Vdc)		h_{FE}	20	40	—	—
Collector-Emitter Saturation Voltage (I_C = 1.0 Adc, I_B = 0.1 Adc)		$V_{CE(sat)}$	—	0.52	1.0	Vdc
Base-Emitter Saturation Voltage (I_C = 1.0 Adc, I_B = 0.1 Adc)		$V_{BE(sat)}$	—	1.05	1.4	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	150	220	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 140 kHz)		C_{obo}	—	8.5	20	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 140 kHz)		C_{ibo}	—	22	80	pF
SWITCHING CHARACTERISTICS						
Delay Time	(V_{CC} = 30 Vdc, $V_{BE(off)}$ = 2.0 Vdc, I_C = 1.0 Adc, I_{B1} = 100 mAdc)	t_d	—	5.0	10	ns
Rise Time		t_r	—	18	30	ns
Storage Time	(V_{CC} = 30 Vdc, I_C = 1.0 Adc, I_{B1} = I_{B2} = 100 mAdc)	t_s	—	45	80	ns
Fall Time		t_f	—	18	30	ns

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(3) f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

FIGURE 1 – DC CURRENT GAIN

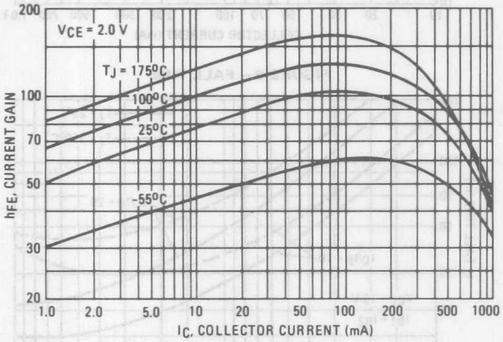


FIGURE 2 – COLLECTOR SATURATION REGION

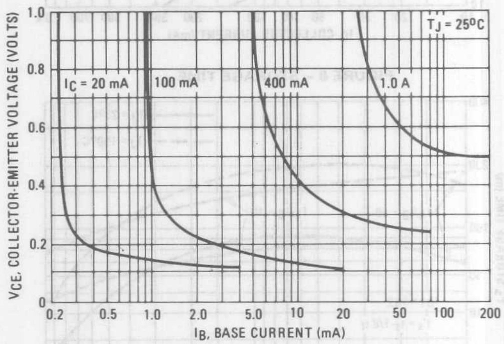


FIGURE 3 – "ON" VOLTAGE

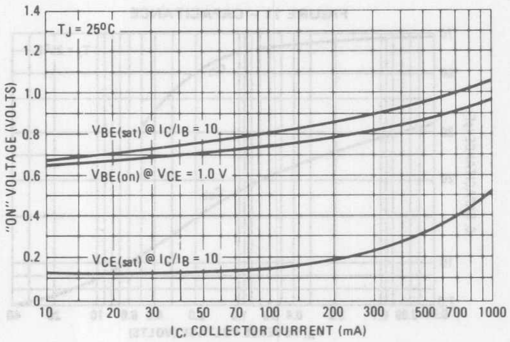
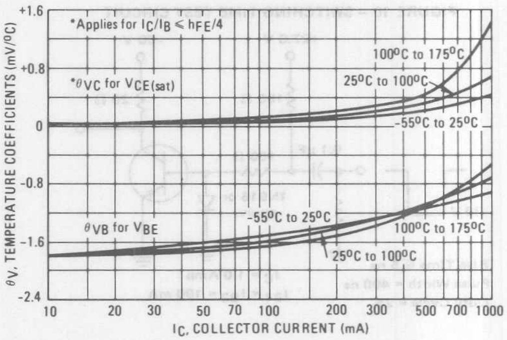


FIGURE 4 – TEMPERATURE COEFFICIENTS



5

FIGURE 5 – ACTIVE REGION SAFE OPERATING AREA

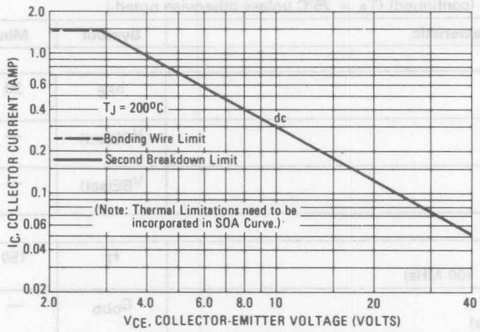


FIGURE 6 – TURN-ON TIME

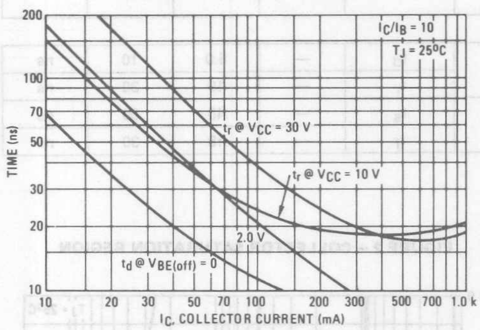


FIGURE 7 – RISE AND FALL TIME

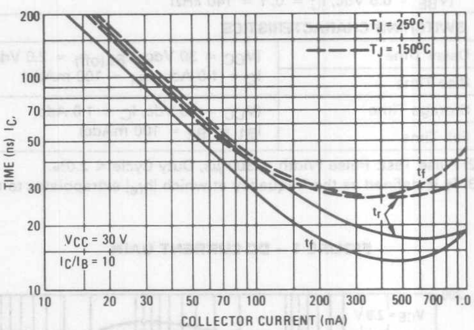


FIGURE 8 – STORAGE TIME

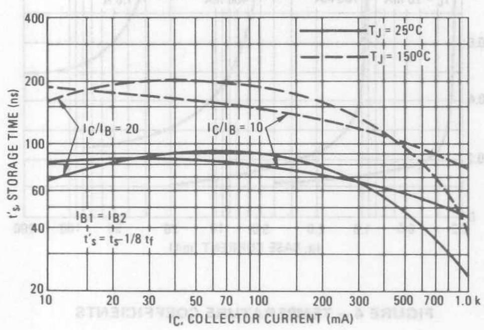


FIGURE 9 – FALL TIME

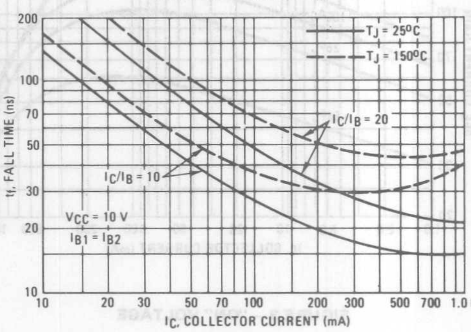


FIGURE 10 – SWITCHING TIME TEST CIRCUIT

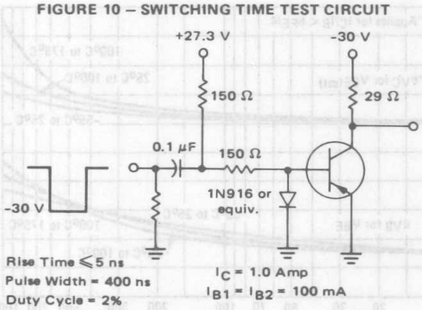
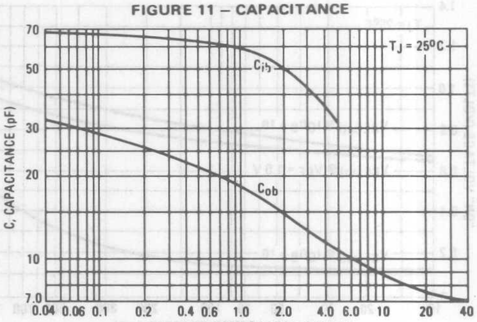
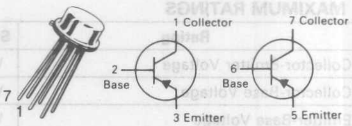


FIGURE 11 – CAPACITANCE



MD4260
MD4261

CASE 654-07, STYLE 1



DUAL RF AMPLIFIER

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	12		Vdc
Collector-Base Voltage	V_{CBO}	12		Vdc
Emitter-Base Voltage	V_{EBO}	4.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
		One Die	Both Die	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	550 3.14	600 3.42	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.4 8.0	2.0 11.4	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Junction to Ambient	Junction to Case	Unit
Thermal Resistance One Die Effective, Both Die	 319 292	 125 87.5	°C/W
Coupling Factor	83	40	%

Refer to 2N4260 for graphs.

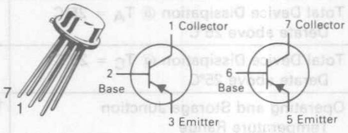
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	12	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	12	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 12$ Vdc, $I_B = 0$)	I_{CEO}	—	1.0	μAdc
Collector Cutoff Current ($V_{CB} = 10$ Vdc, $I_E = 0$)	I_{CBO}	—	10	nAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 30$ mAdc, $V_{CE} = 2.0$ Vdc)	h_{FE}	30 20	200 —	
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$		0.3	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$		1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product ($I_C = 0.5$ mAdc, $V_{CE} = 4.0$ Vdc, f = 100 MHz) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	1.0 1.5	 —	GHz
Output Capacitance ($V_{CB} = 3.0$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	2.5	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz)	C_{ibo}	—	2.5	pF
Collector Base Time Constant ($I_C = 5.0$ mAdc, $V_{CE} = 4.0$ Vdc, f = 31.8 MHz) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 31.8 MHz)	$r_b'C_c$	— —	35 30	ps
MATCHING CHARACTERISTICS (MD4261 only)				
DC Current Gain Ratio(1) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE1}/h_{FE2}	0.8	1.0	—
Base-Emitter Voltage Differential ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc)	$\lvert V_{BE1}-V_{BE2}\rvert$	—	10	mVdc

(1) The lowest h_{FE} reading is taken as h_{FE1} for this ratio.

5

CASE 654-07, STYLE 1



DUAL
AMPLIFIER TRANSISTOR

PNP SILICON

Refer to 2N3307 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	15		Vdc
Collector-Base Voltage	V_{CBO}	20		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current Continuous	I_C	50		mAdc
		One Side	Both Sides	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 1.7	400 2.3	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 3.0 mAdc, I_B = 0)		$V_{(BR)CEO}$	15	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	20	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 15 Vdc, I_E = 0) (V_{CB} = 15 Vdc, I_E = 0, T_A = 150°C)		I_{CBO}	—	—	0.010 1.0	μAdc
ON CHARACTERISTICS						
DC Current Gain (I_C = 3.0 mAdc, V_{CE} = 1.0 Vdc)		h_{FE}	20	50	—	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{CE(sat)}$	—	—	0.4	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{BE(sat)}$	—	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product (I_C = 4.0 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	600	900	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 140 kHz)		C_{obo}	—	—	1.7	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 140 kHz)		C_{ibo}	—	—	2.0	pF
Noise Figure (I_C = 1.0 mAdc, V_{CE} = 6.0 Vdc, f = 60 MHz, R_S = 400 ohms)		NF	—	3.0	6.0	dB
FUNCTIONAL TEST						
Amplifier Power Gain (I_C = 6.0 mAdc, V_{CB} = 12 Vdc, R_G = R_L = 50 ohms, f = 200 MHz)		G_{pe}	15	20	—	dB
MATCHING CHARACTERISTICS						
DC Current Gain Ratio(1) (I_C = 4.0 mAdc, V_{CE} = 10 Vdc)	MD5000 MD5000A MD5000B	h_{FE1}/h_{FE2}	— 0.9 0.8	0.7 — —	— 1.0 1.0	—
Base-Emitter Voltage Differential (I_C = 4.0 mAdc, V_{CE} = 10 Vdc)	MD5000 MD5000A MD5000B	$\lvert V_{BE1}-V_{BE2}\rvert$	— — —	5.0 — —	— 5.0 10	mVdc
Base-Emitter Voltage Differential Gradient (I_C = 4.0 mAdc, V_{CE} = 10 Vdc, T_A = −55 to +125°C)	MD5000 MD5000A MD5000B	$\frac{\Delta(V_{BE1}-V_{BE2})}{\Delta T_A}$	— — —	10 — —	— 10 20	μV/°C

(1) The lowest h_{FE} reading is taken as h_{FE1} for this ratio.

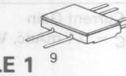
Rating	Symbol	One Die	All Die Equal Power	Unit
Collector-Emitter Voltage	V_{CEO}	30		Vdc
Collector-Base Voltage	V_{CBO}	50	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
Total Device Dissipation @ $T_A = 25°C$	P_D			mW
MD6001,2,3		575	625	
MD6001F,2F		350	400	
MQ6001,2		400	600	
Derate above 25°C				mW/°C
MD6001,2,3		3.29	3.57	
MD6001F,2F		2.0	2.28	
MQ6001,2		2.28	3.42	
Total Device Dissipation @ $T_C = 25°C$	P_D			Watts
MD6001,2,3		1.8	2.5	
MD6001F,2F		1.0	2.0	
MQ6001,2		0.9	3.6	
Derate above 25°C				mW/°C
MD6001,2,3		10.3	14.3	
MD6001F,2F		5.71	11.4	
MQ6001,2		5.13	20.5	
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

MD6003
MQ6001, MQ6002

MD6001
MD6002
MD6003

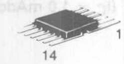
CASE 654-07, STYLE 5

MD6001F
MD6002F



CASE 610A-04, STYLE 1

MQ6001
MQ6002



CASE 607-04, STYLE 1

COMPLEMENTARY DUAL GENERAL PURPOSE TRANSISTOR
NPN/PNP SILICON

5

THERMAL CHARACTERISTICS

Characteristic		Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junction to Case		$R_{\theta JC}$			°C/W
	MD6001,2,3		97	70	
	MD6001F,2F		175	87.5	
	MQ6001,2		195	48.8	
Thermal Resistance, Junction to Ambient		$R_{\theta JA}$(1)			°C/W
	MD6001,2,3		304	280	
	MD6001F,2F		500	438	
	MQ6001,2		438	292	
			Junction to Ambient	**Junction to Class**	
Coupling Factor					%
	MD6001,2,3		84	44	
	MD6001F,2F		75	0	
	MQ6001,2 (Q1-Q2)		57	0	
	(Q1-Q3 or Q1-Q4)		55	0	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

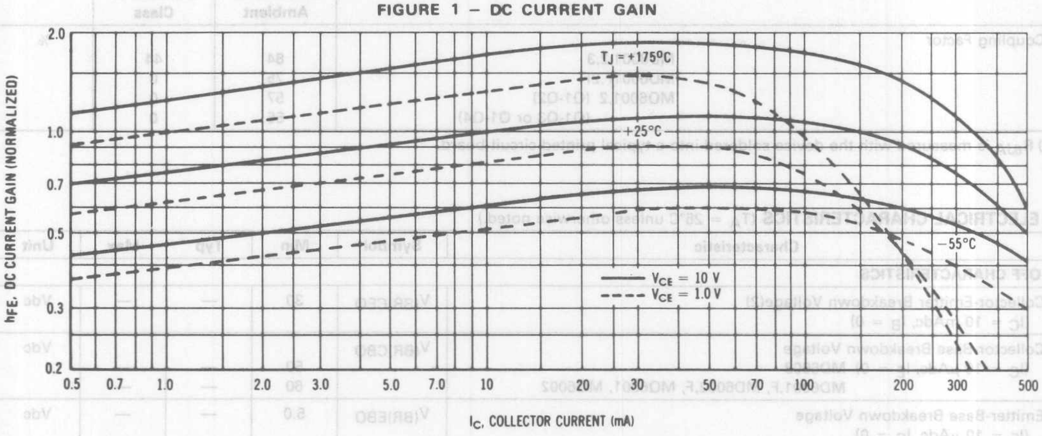
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)		$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	MD6003	$V_{(BR)CBO}$	50	—	—	Vdc
	MD6001,F, MD6002,F, MQ6001, MQ6002		60	—	—	
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Base Cutoff Current		I_{BEV}				nAdc
(V_{CE} = 30 Vdc, V_{BE} = 3.0 Vdc)	MD6003		—	—	50	
(V_{CE} = 50 Vdc, V_{EB} = 3.0 Vdc)	MD6001,F,2,F, MQ6002,F		—	—	30	

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
Collector Cutoff Current		I_{CEV}				
(V_{CE} = 30 Vdc, $V_{BE(off)}$ = 3.0 Vdc)	MD6003		—	—	30	nAdc
(V_{CE} = 50 Vdc, $V_{EB(off)}$ = 3.0 Vdc)	MD6001,F,2,F, MQ6001,2		—	—	20	nAdc
(V_{CE} = 50 Vdc, $V_{EB(off)}$ = 3.0 Vdc, T_A = 150°C)	MD6001,F,2,F, MQ6001,2		—	—	30	μAdc
Collector Cutoff Current (V_{CB} = 40 Vdc, I_E = 0)	MD6003,F	I_{CBO}	—	—	100	nA
ON CHARACTERISTICS(2)						
DC Current Gain		h_{FE}				
(I_C = 0.1 mAdc, V_{CE} = 10 Vdc)	MD6001,F, MQ6001		20	80	—	
	MD6002,F, MQ6002		35	70	—	
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)	MD6001,F, MQ6001		25	90	—	
	MD6003		40	70	—	
	MQ6002,F, MQ6002		50	100	—	
(I_C = 10 mAdc, V_{CE} = 10 Vdc)	MD6001,F, MQ6001		35	70	—	
	MD6002,F, MQ6002		75	110	—	
(I_C = 150 mAdc, V_{CE} = 10 Vdc)	MD6001,F, MQ6001		40	—	120	
	MD6003		70	110	—	
	MD6002,F, MQ6002		100	200	300	
(I_C = 300 mAdc, V_{CE} = 10 Vdc)	MD6001,F, MQ6001		20	—	—	
	All Other Devices		30	90	—	
(I_C = 150 mAdc, V_{CE} = 10 Vdc)	MD6001,F, MQ6001		20	80	—	
	MD6002,F, MQ6002		50	—	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$				Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)	All Devices		—	0.3	0.4	
(I_C = 300 mAdc, I_B = 30 mAdc)	MD6001, MD6002,F, MQ6002,1		—	0.59	1.4	
Base-Emitter Saturation Voltage		$V_{BE(sat)}$				Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)	All Devices		—	1.02	1.3	
(I_C = 300 mAdc, I_B = 30 mAdc)	MD6001, MD6002,F, MQ6001,2		—	1.25	2.0	

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — DC CURRENT GAIN



5

FIGURE 2 – "ON" VOLTAGES

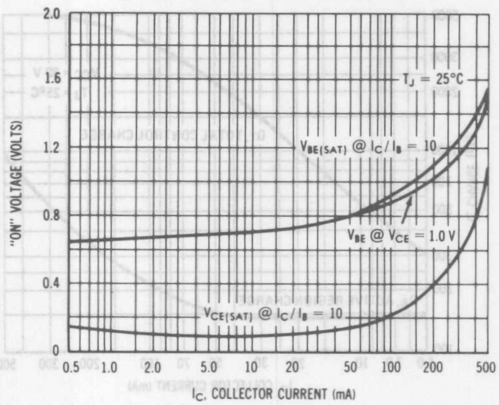
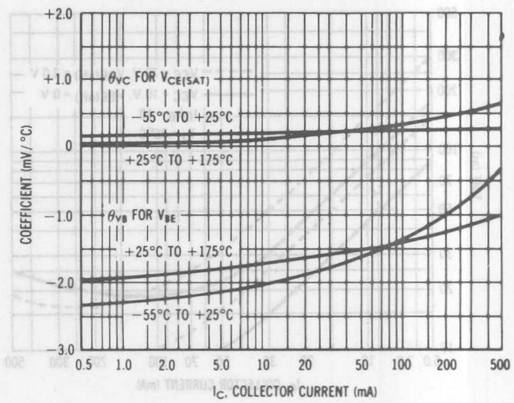


FIGURE 3 – TEMPERATURE COEFFICIENTS



NOISE FIGURE
$V_{CE} = 10$ V, $T_A = 25°C$

FIGURE 4 – FREQUENCY EFFECTS

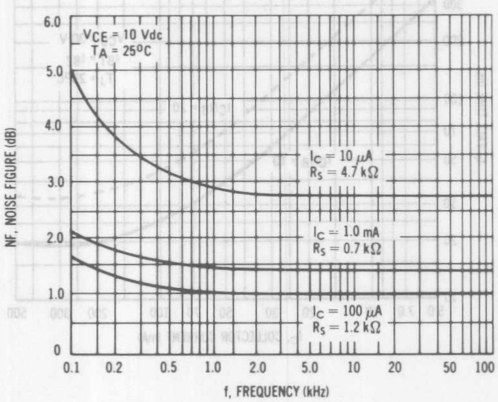


FIGURE 5 – SOURCE RESISTANCE EFFECTS

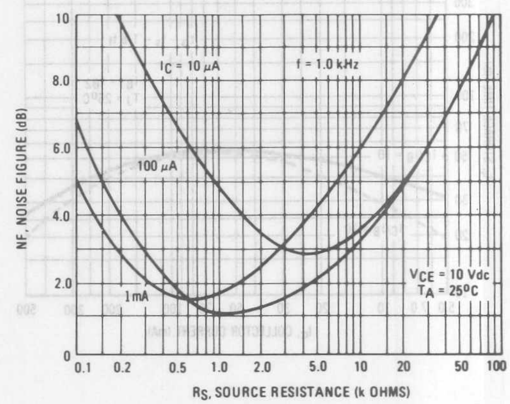


FIGURE 6 – CURRENT-GAIN BANDWIDTH PRODUCT

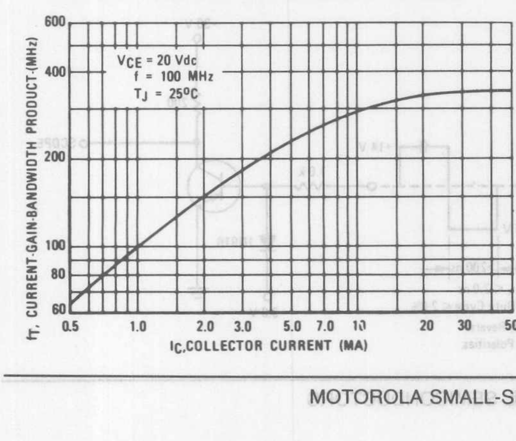
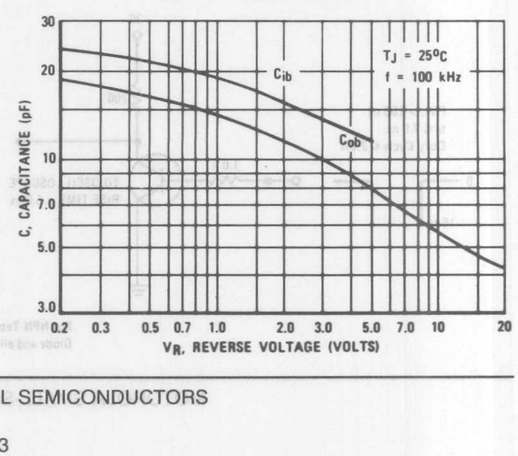
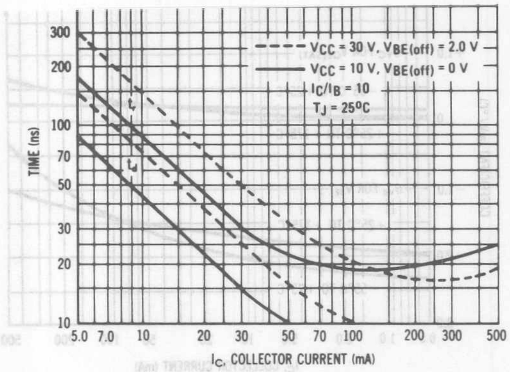


FIGURE 7 – CAPACITANCE





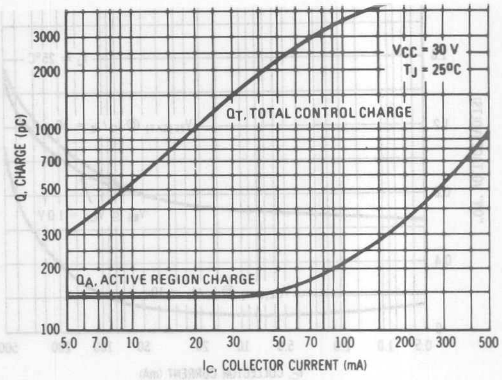


FIGURE 10 – STORAGE TIME

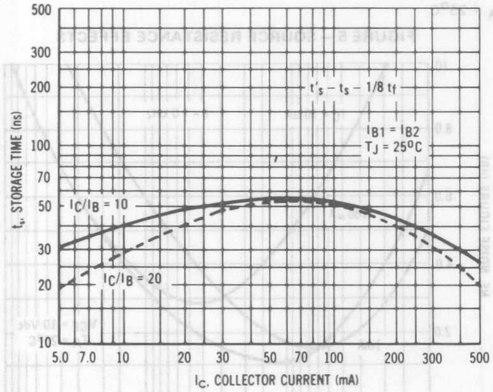


FIGURE 11 – FALL TIME

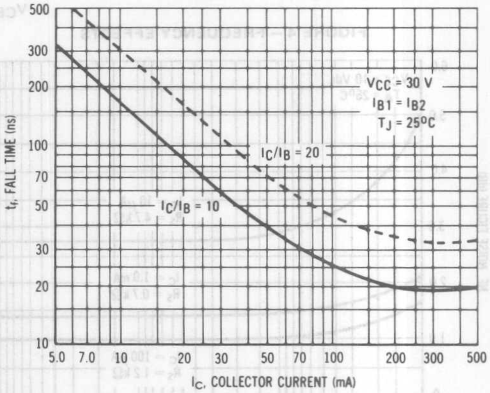


FIGURE 12 – DELAY AND RISE TIME TEST CIRCUIT

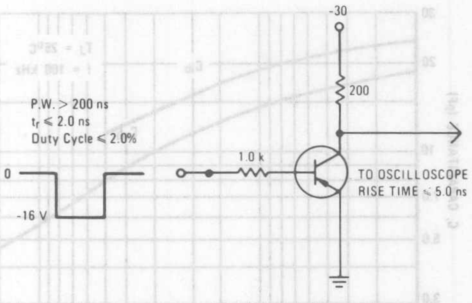
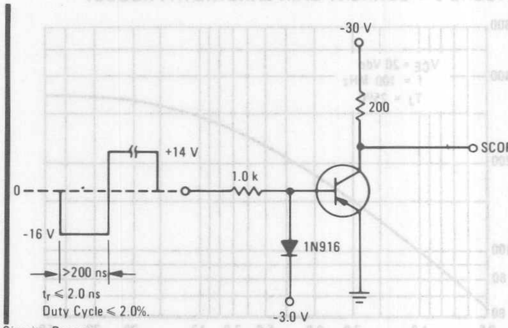


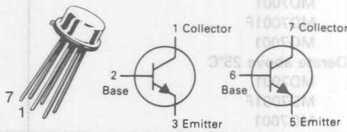
FIGURE 13 – STORAGE AND FALL TIME TEST CIRCUIT



For NPN Test Circuits, Reverse Diode and all Voltage Polarities.

MD7000

CASE 654-07, STYLE 1



DUAL GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to MD2218 for graphs.

Collector-Base Voltage	V_{CBO}	50		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
		One Die	**Both Die**	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	 575 3.29	 625 3.57	 mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	 1.8 10.3	 2.5 14.3	 Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	One Die	Both Die	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	97	70	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	304	280	°C/W
		Junction to Ambient	**Junction to Case**	
Coupling Factor		84	44	%

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	50	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 40 Vdc, I_E = 0)	I_{CBO}	—	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain(2) (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 150 mAdc, V_{CE} = 10 Vdc) (I_C = 300 mAdc, V_{CE} = 10 Vdc)	h_{FE}	 40 70 30	 60 80 50	 — — —	—
Collector-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{CE(sat)}$	—	0.2	0.4	Vdc
Base-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{BE(sat)}$	—	0.95	1.3	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	200	250	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	3.5	8.0	pF
Input Capacitance (V_{EB} = 2.0 Vdc, I_C = 0, f = 100 kHz)	C_{ibo}	—	15	30	pF

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MAXIMUM RATINGS

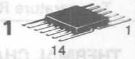
Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	30		Vdc
Collector-Base Voltage	V_{CBO}	50		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	600		mAdc
		One Die	All Die	
Total Device Dissipation @ $T_A = 25°C$	P_D			mW
MD7001		600	650	
MD7001F		350	400	
MQ7001		400	600	
Derate above 25°C				mW/°C
MD7001		3.42	3.7	
MD7001F		2.0	2.28	
MQ7001		2.28	3.42	
Total Device Dissipation @ $T_C = 25°C$	P_D			Watts
MD7001		2.1	3.8	
MD7001F		1.25	2.5	
MQ7001		1.0	4.0	
Derate above 25°C				mW/°C
MD7001		12	17.2	
MD7001F		7.15	14.3	
MQ7001		5.71	22.8	
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

MD7001,F
MQ7001

MD7001
CASE 654-07, STYLE 1

MD7001F
CASE 610A-04, STYLE 1

MQ7001
CASE 607-04, STYLE 1



DUAL
AMPLIFIER TRANSISTOR
PNP SILICON

5

THERMAL CHARACTERISTICS

Characteristic		Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junction to Case		$R_{\theta JC}$			°C/W
	MD7001		83.3	58.3	
	MD7001F		140	70	
	MQ7001		175	43.8	
Thermal Resistance, Junction to Ambient		$R_{\theta JA}$(1)			°C/W
	MD7001		292	270	
	MD7001F		500	438	
	MQ7001		438	292	
			Junction to Ambient	Junction to Case	
Coupling Factor					%
	MD7001		85	40	
	MD7001F		75	0	
	MQ7001 (Q1-Q2)		57	0	
	(Q1-Q3 or Q1-Q4)		55	0	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	50	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 40$ Vdc, $I_E = 0$)	I_{CBO}	—	—	100	nAdc
ON CHARACTERISTICS(2)					
DC Current Gain	h_{FE}				—
($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc)		40	50	—	
($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)		70	90	—	
($I_C = 300$ mAdc, $V_{CE} = 10$ Vdc)		30	60	—	
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{CE(sat)}$	—	0.25	0.4	Vdc

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

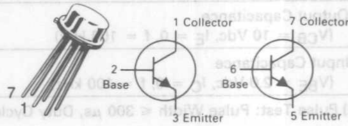
Characteristic	Symbol	Min	Typ	Max	Unit
Base-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{BE(sat)}$	—	0.88	1.3	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	200	320	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	5.8	8.0	pF
Input Capacitance (V_{BE} = 2.0 Vdc, I_C = 0, f = 100 kHz)	C_{ibo}	—	16	30	pF

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

5

MD7002,A,B

CASE 654-07, STYLE 1



DUAL AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N2919 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value: One Die	Value: Both Die Equal Power	Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CBO}	50		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	30		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	575 3.29	625 3.57	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.8 10.3	2.5 14.3	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	One Die	Both Die Equal Power	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	97	70	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	304	280	°C/W
		Junction to Ambient	Junction to Case	
Coupling Factors		84	44	%

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

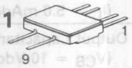
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)		$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	50	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)		I_{CBO}	—	—	100	nAdc
ON CHARACTERISTICS						
DC Current Gain(2) (I_C = 100 μAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc)		h_{FE}	40 50	130 170	— —	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{CE(sat)}$	—	0.2	0.35	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{BE(sat)}$	—	0.8	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product(2) (I_C = 5.0 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)		f_T	200	260	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	2.6	6.0	pF
Input Capacitance (V_{BE} = 2.0 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	2.3	8.0	pF
MATCHING CHARACTERISTICS						
DC Current Gain Ratio(3) (I_C = 100 μAdc, V_{CE} = 10 Vdc)	MD7002A MD7002B	h_{FE1}/h_{FE2}	0.75 0.85	— —	1.0 1.0	—
Base-Emitter Voltage Differential (I_C = 100 μAdc, V_{CE} = 10 Vdc)	MD7002A MD7002B	$\|V_{BE1}-V_{BE2}\|$	— —	— —	25 15	mVdc

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(3) The lowest h_{FE} reading is taken as h_{FE1} for this ratio.

Collector-Base Voltage	V_{CBO}	50		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
		One Die	All Die Equal Power	
Total Device Dissipation @ T_A = 25°C	P_D			mW
MD7003,A,B		550	600	
MD7003,AF		350	400	
MQ7003		400	600	
Derate above 25°C				mW/°C
MD7003,A,B		3.14	3.42	
MD7003,AF		2.0	2.28	
MQ7003		2.28	3.42	
Total Device Dissipation @ T_C = 25°C	P_D			Watts
MD7003,A,B		1.4	2.0	
MD7003,AF		0.7	1.4	
MQ7003		0.7	2.8	
Derate above 25°C				mW/°C
MD7003,A,B		8.0	11.4	
MD7003,AF		4.0	8.0	
MQ7003		4.0	16	
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

MD7003,A,B
CASE 654-07, STYLE 1

MD7003,AF
CASE 610A-04, STYLE 1



MQ7003
CASE 607-04, STYLE 1

DUAL AMPLIFIER TRANSISTOR

PNP SILICON

Refer to 2N3810 for curves.

THERMAL CHARACTERISTICS

Characteristic		Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junction to Case		$R_{\theta JC}$			°C/W
	MD7003,A,B		125	87.5	
	MD7003,AF		250	125	
	MQ7003		250	62.6	
Thermal Resistance, Junction to Ambient		$R_{\theta JA}$(1)			°C/W
	MD7003,A,B		319	292	
	MD7003,AF		500	438	
	MQ7003		438	292	
			Junction to Ambient	Junction to Case	
Coupling Factor					%
	MD7003,A,B		83	40	
	MD7003,AF		75	0	
	MQ7003 (Q1-Q2)		57	0	
	(Q1-Q3 or Q1-Q4)		55	0	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	50	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	—	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain(2)	h_{FE}				—
(I_C = 100 μAdc, V_{CE} = 10 Vdc)		40	350	—	
(I_C = 10 mAdc, V_{CE} = 10 Vdc)		50	350	—	

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

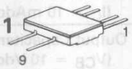
Characteristic		Symbol	Min	Typ	Max	Unit
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{CE(sat)}$	—	0.25	0.35	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)		$V_{BE(sat)}$	—	0.6	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product (I_C = 5.0 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)		f_T	200	300	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	3.0	6.0	pF
Input Capacitance (V_{BE} = 2.0 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	2.0	8.0	pF
Noise Figure (I_C = 100 μAdc, V_{CE} = 10 Vdc, R_S = 3.0 kohms, f = 10 Hz to 15.7 kHz)		NF	—	2.0	—	dB
MATCHING CHARACTERISTICS						
DC Current Gain Ratio(3) (I_C = 100 μAdc, V_{CE} = 10 Vdc)		h_{FE1}/h_{FE2}				—
	MD7003A,AF		0.75	—	1.0	
	MD7003B		0.85	—	1.0	
Base-Emitter Voltage Differential (I_C = 100 μAdc, V_{CE} = 10 Vdc)		$\lvert V_{BE1}-V_{BE2}\rvert$				mV
	MD7003A,AF		—	—	25	
	MD7003B		—	—	15	

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(3) The lowest h_{FE} reading is taken as h_{FE1} for this ratio.

MD7007,A,B,F,BF
MQ7007

MD7007,A,B
CASE 654-07, STYLE 1

MD7007F,BF
CASE 610A-04, STYLE 1



MQ7007
CASE 607-04, STYLE 1

DUAL AMPLIFIER TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CBO}	50		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
		One Die	All Die Equal Power	
Total Device Dissipation @ T_A = 25°C	P_D			mW
MD7007,A,B		575	625	
MD7007F,BF		350	400	
MQ7007		400	600	
Derate above 25°C				mW/°C
MD7007,A,B		3.29	3.57	
MD7007F,BF		2.0	2.28	
MQ7007		2.28	3.42	
Total Device Dissipation @ T_C = 25°C	P_D			Watts
MD7007,A,B		1.8	2.5	
MD7007F,BF		1.0	2.0	
MQ7007		0.9	3.6	
Derate above 25°C				mW/°C
MD7007,A,B		10.3	14.3	
MD7007F,BF		5.71	11.4	
MQ7007		5.13	20.5	
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic		Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junction to Case		$R_{\theta JC}$			°C/W
	MD7007,A,B		97	70	
	MD7007F,BF		175	87.5	
	MQ7007		195	48.8	
Thermal Resistance, Junction to Ambient		$R_{\theta JA}$(1)			°C/W
	MD7007,A,B		304	280	
	MD7007F,BF		500	438	
	MQ7007		438	292	
			Junction to Ambient	Junction to Case	
Coupling Factors					%
	MD7007,A,B		84	44	
	MD7007F,BF		75	0	
	MQ7007 (Q1-Q2)		57	0	
	(Q1-Q2 or Q1-Q4)		55	0	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	50	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	—	—	100	nAdc
ON CHARACTERISTICS(2)					
DC Current Gain	h_{FE}				—
(I_C = 100 μAdc, V_{CE} = 10 Vdc)		30	110	—	
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)		30	130	—	
(I_C = 10 mAdc, V_{CE} = 10 Vdc)		30	75	—	
(I_C = 50 mAdc, V_{CE} = 10 Vdc)		15	25	—	

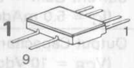
Characteristic		Symbol	Min	Typ	Max	Unit
Collector-Emitter Saturation Voltage (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{CE(sat)}$	—	0.38	1.0	Vdc
Base-Emitter Saturation Voltage (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{BE(sat)}$	—	0.9	1.5	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product(2) (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	300	600	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	4.0	8.0	pF
Input Capacitance (V_{BE} = 2.0 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	3.8	10	pF
MATCHING CHARACTERISTICS						
DC Current Gain Ratio(3) (I_C = 1.0 mAdc, V_{CE} = 10 Vdc)		h_{FE1}/h_{FE2}			—	
	MD7007A		0.75	—	1.0	
	MD7007B		0.85	—	1.0	
Base-Emitter Voltage Differential (I_C = 1.0 mAdc, V_{CE} = 10 Vdc)		$\|V_{BE1}-V_{BE2}\|$				mVdc
	MD7007A		—	—	20	
	MD7007B		—	—	10	

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(3) The lowest h_{FE} reading is taken as h_{FE1} for this ratio.

Rating	Symbol	One Die	All Die Equal Power	Unit
Collector-Base Voltage	V_{CBO}	50		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
		One Die	All Die Equal Power	
Total Device Dissipation @ T_A = 25°C MD7021 MD7021F MQ7021 Derate above 25°C MD7021 MD7021F MQ7021	P_D	 550 350 400 3.14 2.0 2.28	 600 400 600 3.42 2.28 3.42	mW mW/°C
Total Device Dissipation @ T_C = 25°C MD7021 MD7021F MQ7021 Derate above 25°C MD7021 MD7021F MQ7021	P_D	 1.4 0.7 0.7 8.0 4.0 4.0	 2.0 1.4 2.8 11.4 8.0 16	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

MD7021
CASE 654-07, STYLE 5

MD7021F
CASE 610A-04, STYLE 1



MQ7021
CASE 607-04, STYLE 1

COMPLEMENTARY GENERAL PURPOSE TRANSISTOR

NPN/PNP SILICON

THERMAL CHARACTERISTICS

Characteristic		Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junction to Case	MD7021 MD7021F MQ7021	$R_{\theta JC}$	125 250 250	87.5 125 62.6	°C/W
Thermal Resistance, Junction to Ambient	MD7021 MD7021F MQ7021	$R_{\theta JA}$(1)	319 500 438	292 438 292	°C/W
			Junction to Ambient	**Junction to Case**	
Coupling Factor	MD7021 MD7021F MQ7021 (Q1-Q2) (Q1-Q3 or Q1-Q4)		83 75 57 55	40 0 0 0	%

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	50	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	—	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 100 μAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc)	h_{FE}	 40 50	 65 70	 — —	—

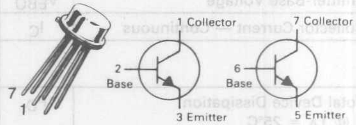
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)(2)	$V_{CE(sat)}$	—	—	0.35	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{BE(sat)}$	—	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 5.0 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	200	320	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	—	6.0	pF
Input Capacitance (V_{BE} = 2.0 Vdc, I_C = 0, f = 100 kHz)	C_{ibo}	—	—	8.0	pF
SWITCHING CHARACTERISTICS					
Turn-On Time (V_{CC} = 30 Vdc, $V_{BE(off)}$ = 0.5 Vdc, I_C = 150 mAdc, I_{B1} = 15 Adc)	t_{on}	—	28	—	ns
Turn-Off Time (V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_{off}	—	72	—	ns

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MD8001
MD8002
MD8003

CASE 654-07, STYLE 1



DUAL AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N2920 for graphs.

5

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}			Vdc
MD8001		40		
MD8002		50		
MD8003		60		
Collector Current — Continuous	I_C	30		mAdc
		One Die	Both Die Equal Power	
Total Device Dissipation @ $T_A = 25°C$	P_D	575	625	mW
Derate above 25°C		3.29	3.57	mW/°C
Total Device Dissipation @ $T_C = 25°C$	P_D	1.8	2.5	Watts
Derate above 25°C		10.3	14.3	mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	One Die Max	Both Die Equal Power Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	97	70	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	304	280	°C/W
		Junction to Ambient	Junction to Case	
Coupling Factor		84	44	%

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

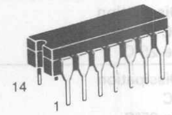
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$				Vdc
	MD8001		40	—	—	
	MD8002		50	—	—	
	MD8003		60	—	—	
Collector Cutoff Current ($V_{CB} = 40$ Vdc, $I_E = 0$)		I_{CBO}	—	—	50	nAdc
Emitter Cutoff Current ($V_{EB} = 4.0$ Vdc, $I_C = 0$)		I_{EBO}	—	—	50	nAdc
ON CHARACTERISTICS						
DC Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc)		h_{FE}	100	200		
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product(2) ($I_C = 5.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)		f_T	—	260	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)		C_{obo}	—	2.6	—	pF
Input Capacitance ($V_{BE} = 2.0$ Vdc, $I_C = 0$, f = 100 kHz)		C_{ibo}	—	2.3	—	pF
MATCHING CHARACTERISTICS						
Base-Emitter Voltage Differential ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc)		$\lvert V_{BE1}-V_{BE2}\rvert$	—	—	15	mVdc

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MHQ918

CASE 632-02, STYLE 1
TO-116



QUAD
AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MD918 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	15		Vdc
Collector-Base Voltage	V_{CBO}	30		Vdc
Emitter-Base Voltage	V_{EBO}	3.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
		Each Transistor	Total Device	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	 0.65 3.72	 1.9 10.88	 Watts mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	 1.3 7.43	 4.6 26.3	 Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

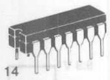
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 3.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	15	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 1.0$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	30	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_E = 0$)	I_{CBO}	—	—	10	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 3.0$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	 — 20 —	 110 80 50	 — — —	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	0.11	0.4	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	—	0.84	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	600	850	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 140 kHz)	C_{obo}	—	0.75	2.0	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 140 kHz)	C_{ibo}	—	1.4	2.5	pF
Noise Figure ($I_C = 1.0$ mAdc, $V_{CE} = 6.0$ Vdc, $R_S = 400$ Ohms, f = 60 MHz)	NF	—	4.0	6.0	dB

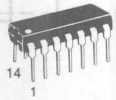
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MPQ2221*
MPQ2222*

MHQ2222
CASE 632-02, STYLE 1
TO-116



MPQ2221
MPQ2222
CASE 646-06, STYLE 1



QUAD
GENERAL PURPOSE TRANSISTOR

NPN SILICON

Refer to MD2218 for graphs.

5

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	30		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
		Each Transistor	Total Device	
Total Device Dissipation @ $T_A = 25°C$	P_D	0.65	1.9	Watts
Derate above 25°C				
MHQ2222		3.72	10.88	mW/°C
MPQ2221, MPQ2222		5.2	15.2	
Operating and Storage Junction Temperature Range MHQ2222	T_J, T_{stg}	−65 to +200		°C
MPQ2221,22		−55 to +150		

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)		$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$)		I_{CBO}	—	—	50	nAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)		I_{EBO}	—	—	50	nAdc
ON CHARACTERISTICS						
DC Current Gain(1)		h_{FE}				—
($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc)	MPQ2221		35	—	—	
	MHQ2222, MPQ2222		75	—	—	
($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)	MPQ2221		40	—	—	
	MHQ2222, MPQ2222		100	—	—	
($I_C = 300$ mAdc, $V_{CE} = 10$ Vdc)	MPQ2221		20	—	—	
	MHQ2222, MPQ2222		30	—	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$				Vdc
($I_C = 150$ mAdc, $I_B = 15$ mAdc)			—	—	0.4	
($I_C = 300$ mAdc, $I_B = 30$ mAdc)			—	—	1.6	
Base-Emitter Saturation Voltage		$V_{BE(sat)}$				Vdc
($I_C = 150$ mAdc, $I_B = 15$ mAdc)			—	—	1.3	
($I_C = 300$ mAdc, $I_B = 30$ mAdc)			—	—	2.6	
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product(1) ($I_C = 20$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)		f_T	200	350	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1 MHz)		C_{obo}	—	4.5	8.0	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1 MHz)		C_{ibo}	—	17	30	pF
SWITCHING CHARACTERISTICS						
Turn-On Time ($V_{CC} = 30$ Vdc, $V_{BE(off)} = 0.5$ Vdc, $I_C = 150$ mAdc, $I_{B1} = 15$ mAdc)		t_{on}	—	25	—	ns
Turn-Off Time ($V_{CC} = 30$ Vdc, $I_C = 150$ mAdc, $I_{B1} = I_{B2} = 15$ mAdc)		t_{off}	—	250	—	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
*MPQ2221A and MPQ2222A also available.

5

FIGURE 1 – DELAY AND RISE TIME EQUIVALENT TEST CIRCUIT

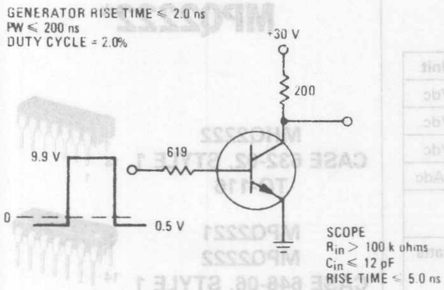
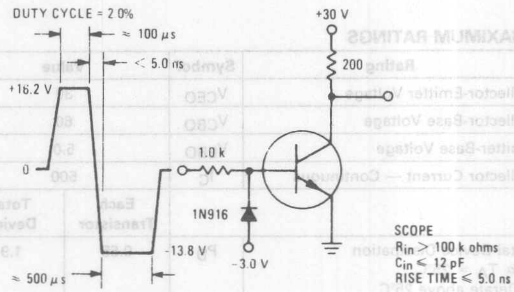
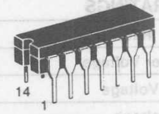


FIGURE 2 – STORAGE TIME AND FALL TIME EQUIVALENT TEST CIRCUIT

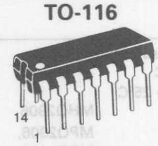


MHQ2369
MPQ2369

MHQ2369
CASE 632-02, STYLE 1



MPQ2369
CASE 646-06, STYLE 1
TO-116



QUAD
SWITCHING TRANSISTOR
NPN SILICON

Refer to MD2369 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	15		Vdc
Collector-Base Voltage	V_{CBO}	40		Vdc
Emitter-Base Voltage	V_{EBO}	4.5		Vdc
Collector Current — Continuous	I_C	500		mAdc
		Each Transistor	Total Device	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C MHQ2369 MPQ2369	P_D	 0.5 2.86 5.0	 1.5 8.58 15	 Watts mW/°C
Operating and Storage Junction Temperature Range MHQ2369 MPQ2369	T_J, T_{stg}	 −65 to +200 −55 to +125		°C

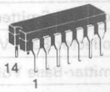
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	15	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	4.5	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$)	I_{CBO}	—	—	0.4	μAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	0.5	μAdc
ON CHARACTERISTICS					
DC Current Gain(1) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 100$ mAdc, $V_{CE} = 2.0$ Vdc)	h_{FE}	40 20	— —	— —	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	—	0.25	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	—	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	450	550	—	MHz
Output Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 1 MHz)	C_{obo}	—	2.5	4.0	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1 MHz)	C_{ibo}	—	3.0	5.0	pF
SWITCHING CHARACTERISTICS					
Turn-On Time ($V_{CC} = 3.0$ Vdc, $V_{BE} = 1.5$ Vdc, $I_C = 10$ mAdc, $I_{B1} = 3.0$ mAdc)	t_{on}	—	9.0	—	ns
Turn-Off Time ($V_{CC} = 3.0$ Vdc, $I_C = 10$ mAdc, $I_{B1} = 3.0$ mAdc, $I_{B2} = 1.5$ mAdc)	t_{off}	—	15	—	ns

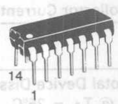
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 2.0%.

MPQ2906*
MPQ2907*

MHQ2906
CASE 632-02, STYLE 1



MPQ2906
MPQ2907
CASE 646-06, STYLE 1
TO-116



QUAD
GENERAL PURPOSE
TRANSISTOR

PNP SILICON

Refer to MD2904 for graphs.

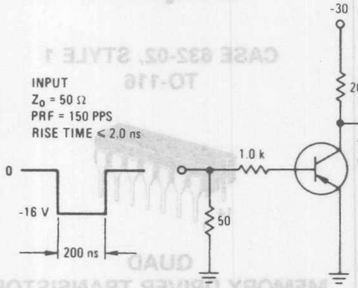
MAXIMUM RATINGS

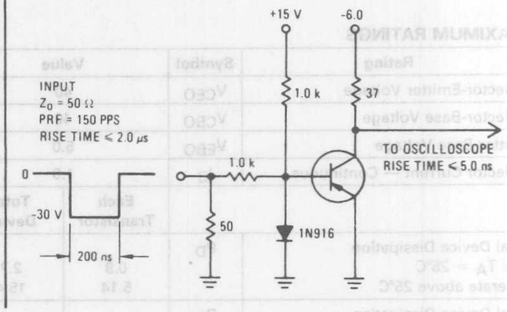
Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	600		mAdc
		Each Transistor	Total Device	
Total Device Dissipation @ T_A = 25°C	P_D	0.65	1.9	Watts
Derate above 25°C MHQ2906		3.72	10.88	mW/°C
MPQ2906, MPQ2907		6.5	19	
Operating and Storage Junction Temperature Range MHQ2906	T_J, T_{stg}	−65 to +200		°C
MPQ2906,07		−55 to +125		

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)		$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)		I_{CBO}	—	—	50	nAdc
Emitter Cutoff Current (V_{CB} = 3.0 Vdc, I_E = 0)		I_{EBO}	—	—	50	nAdc
ON CHARACTERISTICS						
DC Current Gain(1)		h_{FE}				—
(I_C = 10 mAdc, V_{CE} = 10 Vdc)	MHQ2906, MPQ2906		35	—	—	
	MPQ2907		75	—	—	
(I_C = 150 mAdc, V_{CE} = 10 Vdc)	MHQ2906, MPQ2906		40	—	—	
	MPQ2907		100	—	—	
(I_C = 300 mAdc, V_{CE} = 10 Vdc)	MHQ2906, MPQ2906		30	—	—	
	MPQ2907		50	—	—	
Collector-Emitter Saturation Voltage(1)		$V_{CE(sat)}$				Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)			—	—	0.4	
(I_C = 300 mAdc, I_B = 30 mAdc)			—	—	1.6	
Base-Emitter Saturation Voltage(1)		$V_{BE(sat)}$				Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)			—	—	1.3	
(I_C = 300 mAdc, I_B = 30 mAdc)					2.6	
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)		f_T	200	350	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1 MHz)		C_{obo}	—	6.0	8.0	pF
Input Capacitance (V_{BE} = 2.0 Vdc, I_C = 0, f = 1 MHz)		C_{ibo}	—	20	30	pF
SWITCHING CHARACTERISTICS						
Turn-On Time (V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)		t_{on}	—	30	—	ns
Turn-Off Time (V_{CC} = 6.0 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)		t_{off}	—	100	—	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 2.0%.
*MPQ2906A and MPQ2907A also available.

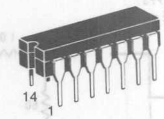

-30
200
INPUT
Z_0 = 50 Ω
PRF = 150 PPS
RISE TIME ≤ 2.0 ns
0
-16 V
200 ns
1.0 k
50
TO OSCILLOSCOPE
RISE TIME ≤ 5.0 ns


+15 V
-6.0
INPUT
Z_0 = 50 Ω
PRF = 150 PPS
RISE TIME ≤ 2.0 μs
0
-30 V
200 ns
1.0 k
37
1.0 k
50
1N916
TO OSCILLOSCOPE
RISE TIME ≤ 5.0 ns

5

MHQ3467

CASE 632-02, STYLE 1
TO-116



QUAD MEMORY DRIVER TRANSISTOR

PNP SILICON

Refer to MD3467 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CBO}	40		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	1.0		Adc
		Each Transistor	Total Device	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.9 5.14	2.7 15.4	Watts mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.8 10.3	6.3 36	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +200		°C

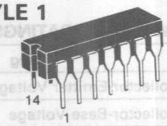
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	—	200	nAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	200	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) ($I_C = 500$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	20	—	—	—
Collector-Emitter Saturation Voltage(1) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	$V_{CE(sat)}$	—	0.23	0.5	Vdc
Base-Emitter Saturation Voltage(1) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	$V_{BE(sat)}$	—	0.9	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(1) ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	125	190	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1 MHz)	C_{obo}	—	10	25	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1 MHz)	C_{ibo}	—	55	80	pF
SWITCHING CHARACTERISTICS					
Turn-On Time ($I_C = 500$ mAdc, $I_{B1} = 50$ mAdc)	t_{on}	—	—	40	ns
Turn-Off Time ($I_C = 500$ mAdc, $I_{B1} = I_{B2} = 50$ mAdc)	t_{off}	—	—	90	ns

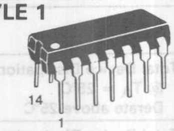
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MHQ3546
MPQ3546

MHQ3546
CASE 632-02, STYLE 1
TO-116



MPQ3546
CASE 646-06, STYLE 1



QUAD
SWITCHING TRANSISTOR
PNP SILICON

MAXIMUM RATINGS

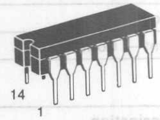
Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	12		Vdc
Collector-Base Voltage	V_{CBO}	15		Vdc
Emitter-Base Voltage	V_{EBO}	4.5		Vdc
Collector Current — Continuous	I_C	200		mAdc
		Each Transistor	**Total Device**	
Total Device Dissipation @ T_A = 25°C Derate above 25°C MHQ3546 MPQ3546	P_D	 0.5 2.86 4.0	 1.5 8.58 12	Watts mW/°C
Operating and Storage Junction MHQ3546 Temperature Range MPQ3546	T_J, T_{stg}	 −65 to +200 −55 to +150		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	12	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	15	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	4.5	—	—	Vdc
Collector Cutoff Current (V_{CB} = 10 Vdc, I_E = 0)	I_{CBO}	—	—	0.1	μAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)	I_{EBO}	—	—	0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain(1) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc) (I_C = 100 mAdc, V_{CE} = 1.0 Vdc)	h_{FE}	 30 15	 — —	 — —	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{CE(sat)}$	—	—	0.25	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{BE(sat)}$	—	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(1) (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	600	1000	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	2.0	6.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	—	3.5	8.0	pF
SWITCHING CHARACTERISTICS					
Turn-On Time (V_{CC} = 2.0 Vdc, $V_{BE(off)}$ = 3.0 Vdc, I_C = 30 mAdc, I_{B1} = 1.5 mAdc)	t_{on}	—	15	—	ns
Turn-Off Time (V_{CC} = 2.0 Vdc, I_C = 30 mAdc, I_{B1} = I_{B2} = 1.5 mAdc)	t_{off}	—	25	—	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

CASE 632-02, STYLE 1
TO-116



QUAD AMPLIFIER TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
		Each Transistor	**Total Device**	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	 0.5 2.86	 1.5 8.58	Watts mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	 1.0 5.71	 3.5 20	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

Refer to 2N3810 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40			Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$)	I_{CBO}	—	—	10	nAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	20	nAdc
ON CHARACTERISTICS					
DC Current Gain(1) ($I_C = 10\ \mu$Adc, $V_{CE} = 5.0$ Vdc) ($I_C = 100\ \mu$Adc, $V_{CE} = 5.0$ Vdc) ($I_C = 500\ \mu$Adc, $V_{CE} = 5.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc)	h_{FE}	 100 150 150 125	 —	 —	—
Collector-Emitter Saturation Voltage ($I_C = 100\ \mu$Adc, $I_B = 10\ \mu$Adc) ($I_C = 1.0$ mAdc, $I_B = 100\ \mu$Adc)	$V_{CE(sat)}$	 — —	 — —	 0.2 0.25	Vdc
Base-Emitter Saturation Voltage ($I_C = 100\ \mu$Adc, $I_B = 10\ \mu$Adc) ($I_C = 1.0$ mAdc, $I_B = 100\ \mu$Adc)	$V_{BE(sat)}$	 — —	 — —	 0.7 0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc, f = 100 MHz)	f_T	—	130	—	MHz
Output Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{obo}	—	2.3	—	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)	C_{ibo}	—	5.5	—	pF
Noise Figure ($I_C = 100\ \mu$Adc, $V_{CE} = 10$ Vdc, $R_S = 3.0$ kohms, f = 10 Hz to 15.7 kHz)	NF	—	2.5		dB

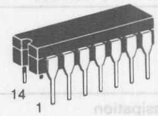
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MHQ4002A

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	45		Vdc
Collector-Emitter Voltage	V_{CES}	70		Vdc
Collector-Base Voltage	V_{CBO}	70		Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	1.5		Adc
		Each Transistor	Four Transistors Equal Power	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	750 4.3	2500 14.3	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.2 6.86	4.0 22.8	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +200		°C

CASE 632-02, STYLE 1
TO-116



QUAD
MEMORY DRIVER TRANSISTOR

NPN SILICON

Refer to MD3725 for graphs.

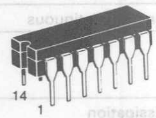
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	45	—	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 10\ \mu$Adc, $V_{BE} = 0$)	$V_{(BR)CES}$	70	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	70	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	6.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	—	500	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 500$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1.0$ Adc, $V_{CE} = 5.0$ Vdc)	h_{FE}	50 30 20	100 60 45	250 — —	
Collector-Emitter Saturation Voltage ($I_C = 100$ mAdc, $I_B = 10$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc) ($I_C = 1.0$ Adc, $I_B = 100$ mAdc)	$V_{CE(sat)}$	— — —	0.14 0.23 0.36	0.26 0.52 0.95	Vdc
Base-Emitter Saturation Voltage ($I_C = 100$ mAdc, $I_B = 10$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc) ($I_C = 1.0$ Adc, $I_B = 100$ mAdc)	$V_{BE(sat)}$	— 0.8 —	0.75 0.88 1.0	0.86 1.1 1.7	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(1) ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	200	275		MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C_{obo}		5.0	10	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1.0 MHz)	C_{ibo}	—	55	70	pF
SWITCHING CHARACTERISTICS					
Turn-On Time ($V_{CC} = 30$ Vdc, $I_C = 0.5$ Adc, $V_{BE} = 3.8$ Vdc, $I_{B1} = 50$ mAdc)	t_{on}	—	30	40	ns
Turn-Off Time ($V_{CC} = 30$ Vdc, $I_C = 0.5$ Adc, $I_{B1} = I_{B2} = 50$ mAdc)	t_{off}	—	60	75	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MHQ4013
MHQ4014

CASE 632-02, STYLE 1
TO-116



QUAD
MEMORY DRIVER TRANSISTOR

NPN SILICON

Refer to MD3725 for graphs.

5

MAXIMUM RATINGS

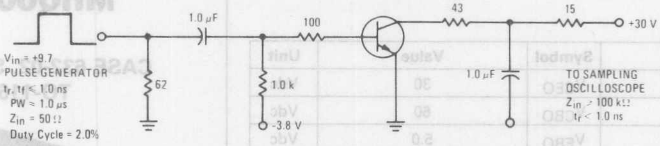
Rating	Symbol	MHQ4013	MHQ4014	Unit
Collector-Emitter Voltage	V_{CEO}	40	45	Vdc
Collector-Emitter Voltage	V_{CES}	60	70	Vdc
Collector-Base Voltage	V_{CBO}	60	70	Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	1.5		Adc
		Each Transistor	**Four Transistors Equal Power**	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	750 4.3	2500 14.3	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.2 6.86	4.0 22.8	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +200		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	MHQ4013 MHQ4014	$V_{(BR)CEO}$	40 45	— —	— —	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 10\ \mu$Adc, $V_{BE} = 0$)	MHQ4013 MHQ4014	$V_{(BR)CES}$	60 70	— —	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	MHQ4013 MHQ4014	$V_{(BR)CBO}$	60 70	— —	— 	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	6.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$)		I_{CBO}	—	—	500	nAdc
ON CHARACTERISTICS(1)						
DC Current Gain	($I_C = 100$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 500$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1.0$ Adc, $V_{CE} = 5.0$ Vdc)	h_{FE}	60 35 25	100 65 50	250 — —	—
Collector-Emitter Saturation Voltage	($I_C = 100$ mAdc, $I_B = 10$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc) ($I_C = 1.0$ Adc, $I_B = 100$ mAdc)	$V_{CE(sat)}$	— — —	0.14 0.23 0.36	0.26 0.52 0.95	Vdc
Base-Emitter Saturation Voltage	($I_C = 100$ mAdc, $I_B = 10$ mAdc) ($I_C = 500$ mAdc, $I_B = 50$ mAdc) ($I_C = 1.0$ Adc, $I_B = 100$ mAdc)	$V_{BE(sat)}$	— 0.8 —	0.75 0.88 1.0	0.86 1.1 1.7	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product(1) ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)		f_T	200	275	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1 MHz)		C_{obo}	—	5.0	10	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1 MHz)		C_{ibo}	—	50	70	pF
SWITCHING CHARACTERISTICS						
Turn-On Time ($V_{CC} = 30$ Vdc, $I_C = 0.5$ Adc, $V_{BE(off)} = 3.8$ Vdc, $I_{B1} = 50$ mAdc)		t_{on}	—	20	35	ns
Turn-Off Time ($V_{CC} = 30$ Vdc, $I_C = 0.5$ Adc, $I_{B1} = I_{B2} = 50$ mAdc)		t_{off}	—	50	60	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

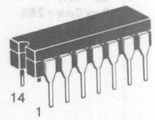
FIGURE 1 – TURN-ON AND TURN-OFF SWITCHING TIMES TEST CIRCUIT



5

MHQ6002

CASE 632-02, STYLE 1
TO-116



QUAD COMPLEMENTARY TRANSISTOR

NPN/PNP SILICON

Refer to MHQ2222 for NPN graphs.*

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	30		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
		Each Transistor	**Total Device**	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.65 3.72	1.9 10.88	Watts mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.3 7.43	4.6 26.3	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

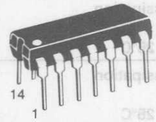
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0)	I_{CBO}	—	—	20	nAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)	I_{EBO}	—	—	30	nAdc
ON CHARACTERISTICS					
DC Current Gain(1)	h_{FE}				—
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc) MHQ6001		25	—	—	
MHQ6002		50	—	—	
(I_C = 10 mAdc, V_{CE} = 10 Vdc) MHQ6001		35	—		
MHQ6002		75	—	—	
(I_C = 150 mAdc, V_{CE} = 10 Vdc) MHQ6001		40	—	—	
MHQ6002		100	—	—	
(I_C = 300 mAdc, V_{CE} = 10 Vdc) MHQ6001		20	—	—	
MHQ6002		30	—		
Collector-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 300 mAdc, I_B = 30 mAdc)	$V_{CE(sat)}$	— —	— —	0.4 1.4	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 300 mAdc, I_B = 30 mAdc)	$V_{BE(sat)}$	— —	— —	1.3 2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(1) (I_C = 50 mAdc, V_{CE} = 20 Vdc, f = 100 kHz)	f_T	—	400	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1 MHz) NPN PNP	C_{obo}	— —	6.0 4.5	— —	pF
Input Capacitance (V_{BE} = 2.0 Vdc, I_C = 0, f = 1 MHz) NPN PNP	C_{ibo}	— —	20 17	— —	pF
SWITCHING CHARACTERISTICS					
Turn-On Time (V_{CC} = 30 Vdc, V_{BE} = 0.5 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_{on}	—	30	—	ns
Turn-Off Time (V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_{off}	— —	225 —	— —	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
*Refer to MHQ2907 for PNP graphs.

MPQ918

CASE 646-06, STYLE 1
TO-116



QUAD
AMPLIFIER TRANSISTOR

NPN SILICON

5

Rating	Symbol	Each Transistor	Four Transistors Equal Power	Unit
Collector-Base Voltage	V_{CBO}	30		Vdc
Emitter-Base Voltage	V_{EBO}	3.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	500 4.0	900 7.2	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	6.7 0.825	2.4 19.2	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic		Junction to Case	Junction to Ambient	Unit
Thermal Resistance	Each Die	151	250	°C/W
	Effective, 4 Die	52	134	°C/W
Coupling Factors	Q1-Q4 or Q2-Q3	34	70	%
	Q1-Q2 or Q3-Q4	2.0	26	%

Refer to MD918 for graphs.

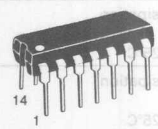
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 3.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	15		—	Vdc
Collector-Base Breakdown Voltage ($I_C = 1.0$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	30	—		Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	3.0			Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_E = 0$)	I_{CBO}	—	—	10	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 3.0$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	— 20 —	110 80 50	— — —	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	0.11	0.4	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	—	0.84	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 4.0$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	600	850	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1 MHz)	C_{obo}	—	0.75	1.7	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1 MHz)	C_{ibo}	—	1.1	2.0	pF
Noise Figure ($I_C = 1.0$ mAdc, $V_{CE} = 6.0$ Vdc, $R_G = 400$ Ohms, f = 60 MHz)	NF	—	4.0	6.0	dB

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MPQ1000

CASE 646-06, STYLE 1
TO-116



QUAD
AMPLIFIER TRANSISTOR
NPN SILICON

Refer to MD2218 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	20		Vdc
Collector-Base Voltage	V_{CBO}	40		Vdc
Emitter-Base Voltage	V_{EBO}	4.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
		Each Transistor	**Four Transistors Equal Power**	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	650 5.18	1250 10	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0	3.0 24	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic		Junction to Case	Junction to Ambient	Unit
Thermal Resistance(1)	Each Die	125	193	°C/W
	Effective, 4 Die	41.6	100	°C/W
Coupling Factors	Q1-Q4 or Q2-Q3	30	60	%
	Q1-Q2 or Q3-Q4	2.0	24	%

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

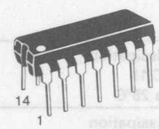
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	20	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	—	—	50	nAdc
Emitter Cutoff Current (V_{EB} = 2.0 Vdc, I_C = 0)	I_{EBO}	—	—	50	nAdc
ON CHARACTERISTICS(2)					
DC Current Gain	h_{FE}				—
(I_C = 10 mAdc, V_{CE} = 10 Vdc)		50	—	—	
(I_C = 50 mAdc, V_{CE} = 10 Vdc)		50	—	—	
(I_C = 150 mAdc, V_{CE} = 10 Vdc)		40	—	—	
Collector-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{CE(sat)}$	—	—	0.5	Vdc
Base-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{BE(sat)}$	—	—	1.3	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	175	—	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1 MHz)	C_{obo}	—	—	8.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1 MHz)	C_{ibo}	—	—	30	pF

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MPQ1500

CASE 646-06, STYLE 1
TO-116



QUAD TRANSISTOR

PNP SILICON

Refer to MPQ2907 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	20		Vdc
Collector-Base Voltage	V_{CBO}	40		Vdc
Emitter-Base Voltage	V_{EBO}	4.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
		Each Transistor	Four Transistors Equal Power	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.65 5.18	1.25 8.0	Watts mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.0 8.0	3.0 24	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Junction to Case	Junction to Ambient	Unit
Thermal Resistance(1) Each Die Effective, 4 Die	 125 41.6	 193 100	°C/W
Coupling Factor Q1-Q4 or Q2-Q3 Q1-Q2 or Q3-Q4	 30 2.0	 60 24	%

(1) Junction to ambient data applies for typical printed circuit board mounting.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

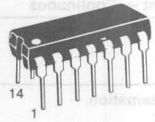
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	20	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu$Adc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu$Adc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	—	50	nAdc
Emitter Cutoff Current ($V_{EB} = 2.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	50	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 150$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	 50 50 40	 100 120 80	 — — —	—
Collector-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{CE(sat)}$	—	0.22	0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 150$ mAdc, $I_B = 15$ mAdc)	$V_{BE(sat)}$	—	0.89	1.3	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(1) ($I_C = 20$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)	f_T	150	300	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 1 MHz)	C_{obo}	—	4.5	8.0	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1 MHz)	C_{ibo}	—	17	30	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

5

MPQ2484

CASE 646-06, STYLE 1
TO-116



QUAD AMPLIFIER TRANSISTOR

NPN SILICON

Refer to 2N2919 for graphs.

5

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
		Each Transistor	**Four Transistors Equal Power**	
Total Device Dissipation @ $T_A = 25°C$(1) Derate above 25°C	P_D	500 4.0	900 7.2	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	0.825 6.7	2.4 19.2	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

(1) Second Breakdown occurs at power levels greater than 3 times the power dissipation rating.

THERMAL CHARACTERISTICS

Characteristic		Junction to Case	Junction to Ambient	Unit
Thermal Resistance	Each Die	151	250	°C/W
	Effective, 4 Die	52	134	°C/W
Coupling Factors	Q1-Q4 or Q2-Q3	34	70	%
	Q1-Q2 or Q3-Q4	2.0	26	%

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)		$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)		$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)		$V_{(BR)EBO}$	6.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 45$ Vdc, $I_E = 0$)		I_{CBO}	—	—	20	nAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)		I_{EBO}	—	—	20	nAdc
ON CHARACTERISTICS						
DC Current Gain(2)		h_{FE}				
($I_C = 0.1$ mAdc, $V_{CE} = 5.0$ Vdc)	MPQ2483 MPQ2484		100 200	— —	— —	
($I_C = 1.0$ mAdc, $V_{CE} = 5.0$ Vdc)	MPQ2483 MPQ2484		150 300	— —	— —	
($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc)	MPQ2483 MPQ2484		150 300	— —	— —	
Collector-Emitter Saturation Voltage ($I_C = 1.0$ mAdc, $I_B = 0.1$ mAdc) ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)		$V_{CE(sat)}$	— —	0.13 0.15	0.35 0.5	Vdc
Base-Emitter Saturation Voltage(2) ($I_C = 100$ μAdc, $V_{CE} = 5.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc)		$V_{BE(sat)}$	— —	0.58 0.70	0.7 0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product ($I_C = 500$ μAdc, $V_{CE} = 5.0$ Vdc, f = 20 MHz)		f_T	50	100	—	MHz
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 1 MHz)		C_{ibo}	—	4.0	8.0	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
Collector-Base Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1 MHz)		C_{cb}	—	1.8	6.0	pF
Noise Figure (I_C = 10 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 kohms, f = 10 Hz to 15.7 kHz, BW = 10 kHz)		NF				dB
	MPQ2483		—	3.0	—	
	MPQ2484		—	2.0	—	

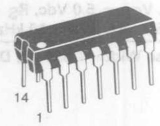
(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

5

MPQ2906, 2907 For Specifications, See MHQ2906 Data.

MPQ3303

CASE 646-06, STYLE 1
TO-116



QUAD
SWITCHING TRANSISTOR

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	12		Vdc
Collector-Base Voltage	V_{CBO}	25		Vdc
Emitter-Base Voltage	V_{EBO}	4.0		Vdc
Collector Current — Continuous	I_C	1.0		Adc
		Each Transistor	Four Transistors Equal Power	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	 650 5.2	 1250 10	 mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	 1.0 8.0	 3.0 24	 Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic		Junction to Case	Junction to Ambient	Unit
Thermal Resistance	Each Die Effective, 4 Die	125 41.6	193* 100*	°C/W °C/W
Coupling Factors	Q1-Q4 or Q2-Q3 Q1-Q2 or Q3-Q4	30 2.0	60 25	% %

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

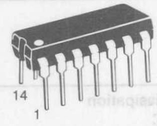
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	12	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	25	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current (V_{CE} = 15 Vdc, V_{BE} = 0)	I_{CES}	—	—	100	μAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 100 mAdc, V_{CE} = 0.5 Vdc) (I_C = 300 mAdc, V_{CE} = 0.5 Vdc)	h_{FE}	 30 40	 45 55	 — 200	—
Collector-Emitter Saturation Voltage (I_C = 300 mAdc, I_B = 30 mAdc) (I_C = 1.0 Adc, I_B = 0.1 Adc)	$V_{CE(sat)}$	 — —	 0.22 0.52	 0.33 0.7	Vdc
Base-Emitter Saturation Voltage (I_C = 300 mAdc, I_B = 30 mAdc) (I_C = 1.0 Adc, I_B = 0.1 Adc)	$V_{BE(sat)}$	 — —	 0.87 1.04	 1.1 1.4	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 100 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)	f_T	400	500	—	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1 MHz)	C_{obo}	—	5.0	10	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 1 MHz)	C_{ibo}	—	22	30	pF
SWITCHING CHARACTERISTICS					
Turn-On Time (V_{CC} = 12 Vdc, I_C = 1.0 Adc, $V_{BE(off)}$ = 4.0 Vdc, I_{B1} = 100 mAdc)	t_{on}	—	12	15	ns
Turn-Off Time (V_{CC} = 12 Vdc, I_C = 1.0 Adc, I_{B1} = I_{B2} = 100 mAdc)	t_{off}	—	18	25	ns

Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	1.0		Adc
		Each Transistor	Four Transistors Equal Power	
Total Device Dissipation @ $T_A = 25°C$(1) Derate above 25°C	P_D	650 5.2	1500 12	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.25 10	3.2 25.6	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

(1) Second Breakdown occurs at power levels greater than 2 times the power dissipation rating.

MPQ3467

CASE 646-06, STYLE 1
TO-116



QUAD
MEMORY DRIVER TRANSISTOR

PNP SILICON

Refer to MD3467 for graphs.

THERMAL CHARACTERISTICS

Characteristic		$R_{\theta JC}$ Junction to Case	$R_{\theta JA}$ Junction to Ambient	Unit
Thermal Resistance	Each Die Effective, 4 Die	100 39	193 83.2	°C/W °C/W
Coupling Factors	Q1-Q4 or Q2-Q3 Q1-Q2 or Q3-Q4	45 5.0	55 10	% %

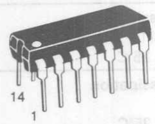
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	—	200	nAdc
Emitter Cutoff Current ($V_{BE} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	200	nAdc
ON CHARACTERISTICS					
DC Current Gain(2) ($I_C = 500$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	20	—	—	—
Collector-Emitter Saturation Voltage(2) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	$V_{CE(sat)}$	—	0.23	0.5	Vdc
Base-Emitter Saturation Voltage(2) ($I_C = 500$ mAdc, $I_B = 50$ mAdc)	$V_{BE(sat)}$	—	0.90	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 50$ mAdc, $V_{CE} = 10$ Vdc, f = 100 MHz)	f_T	125	190	—	MHz
Output Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	10	25	pF
Input Capacitance ($V_{BE} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz)	C_{ibo}	—	55	80	pF
SWITCHING CHARACTERISTICS					
Turn-On Time ($I_C = 500$ mAdc, $I_{B1} = 50$ mAdc)	t_{on}	—	—	40	ns
Turn-Off Time ($I_C = 500$ mAdc, $I_{B1} = I_{B2} = 50$ mAdc)	t_{off}	—	—	90	ns

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MPQ3725,A

CASE 646-06, STYLE 1
TO-116



QUAD
CORE DRIVER TRANSISTOR

NPN SILICON

Refer to MD3725 for graphs.

Rating	Symbol	MPQ3725	MPQ3725A	Unit
Collector-Emitter Voltage	V_{CEO}	40	50	Vdc
Collector-Emitter Voltage	V_{CES}	60	70	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	1.0		Adc
		One Transistor	Four Transistors Equal Power	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.0 8.0	2.5 20	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max		Unit
		One Transistor	Effective For Four Transistors	
Thermal Resistance, Junction to Ambient(1)	$R_{\theta JA}$	125	50	°C/W

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

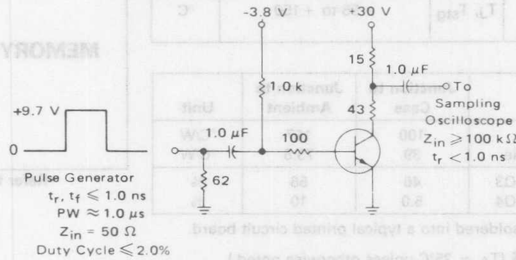
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	MPQ3725 MPQ3725A	$V_{(BR)CEO}$	40 50	— —		Vdc
Collector-Emitter Breakdown Voltage (I_C = 100 μAdc, V_{BE} = 0)	MPQ3725 MPQ3725A	$V_{(BR)CES}$	60 70	— —		Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—		Vdc
Collector Cutoff Current (V_{CB} = 40 Vdc, I_E = 0)		I_{CBO}	—	—	0.5	μAdc
ON CHARACTERISTICS(2)						
DC Current Gain (I_C = 100 mAdc, V_{CE} = 1.0 Vdc)	MPQ3725 MPQ3725A	h_{FE}	35 40	75 80	200 —	
(I_C = 500 mAdc, V_{CE} = 2.0 Vdc)	MPQ3725 MPQ3725A		25 30	45 50	— —	
Collector-Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc)		$V_{CE(sat)}$	—	0.32	0.45	Vdc
Base-Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc)		$V_{BE(sat)}$	0.8	0.9	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	MPQ3725 MPQ3725A	f_T	250 200	275 250	— —	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	5.1	10	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	62	80	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS					
Turn-On Time (I_C = 500 mAdc, I_{B1} = 50 mAdc, $V_{BE(off)}$ = 3.8 Vdc)	t_{on}	—	20	35	ns
Turn-Off Time (I_C = 500 mAdc, I_{B1} = I_{B2} = 50 mAdc)	t_{off}	—	50	60	ns

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — SWITCHING TIMES TEST CIRCUIT



5

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CBO}	40		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	1.5		Adc
		Each Transistor	Four Transistors Equal Power	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	 750 5.98	 1700 13.6	 mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	 1.25 10	 3.2 25.6	 Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

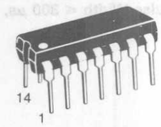
THERMAL CHARACTERISTICS

Characteristic		Junction to Case	Junction to Ambient	Unit
Thermal Resistance(1)	Each Die Effective, 4 Die	100 39	167 73.5	°C/W °C/W
Coupling Factors	Q1-Q4 or Q2-Q3 Q1-Q2 or Q3-Q4	46 5.0	56 10	% %

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

MPQ3762

CASE 646-06, STYLE 1
TO-116



QUAD
MEMORY DRIVER TRANSISTOR

PNP SILICON

Refer to MD3467 for graphs.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	—	—	100	nAdc
Emitter Cutoff Current (V_{EB} = 3.0 Vdc, I_C = 0)	I_{EBO}	—	—	100	nAdc
ON CHARACTERISTICS(2)					
DC Current Gain (I_C = 150 mAdc, V_{CE} = 1.0 Vdc) (I_C = 500 mAdc, V_{CE} = 2.0 Vdc) (I_C = 1.0 Adc, V_{CE} = 2.0 Vdc)	h_{FE}	 35 30 20	 70 65 35	 — — —	—
Collector-Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc) (I_C = 1.0 Adc, I_B = 100 mAdc)	$V_{CE(sat)}$	 — —	 0.3 0.6	 0.55 0.9	Vdc
Base-Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc) (I_C = 1.0 Adc, I_B = 100 mAdc)	$V_{BE(sat)}$	 — —	 0.9 1.0	 1.25 1.4	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	150	275	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	9.0	15	pF
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 100 kHz)	C_{ibo}	—	55	80	pF
SWITCHING CHARACTERISTICS					
Turn-On Time (V_{CC} = 30 Vdc, I_C = 1.0 Adc, I_{B1} = 100 mAdc, $V_{BE(off)}$ = 2.0 Vdc)	t_{on}	—	—	50	ns
Turn-Off Time (V_{CC} = 30 Vdc, I_C = 1.0 Adc, I_{B1} = I_{B2} = 100 mAdc)	t_{off}	—	—	120	ns

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

EQUIVALENT TEST CIRCUITS

FIGURE 1 – TURN-ON

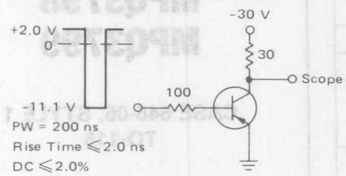
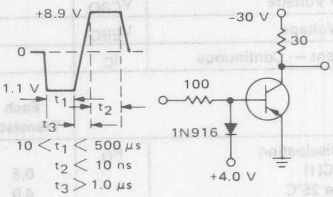


FIGURE 2 – TURN-OFF

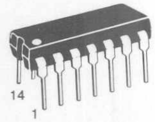


Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
		Each Transistor	Four Transistors Equal Power	
Total Device Dissipation @ T_A = 25°C(1) Derate above 25°C	P_D	0.5 4.0	0.9 7.2	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	0.825 6.7	2.4 19.2	Watts m/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

(1) Second breakdown occurs at power levels greater than 3 times the power dissipation rating.

MPQ3798
MPQ3799

CASE 646-06, STYLE 1
TO-116



QUAD AMPLIFIER TRANSISTOR

PNP SILICON

Refer to 2N3810 for graphs.

5

THERMAL CHARACTERISTICS

Characteristic		$R_{\theta JC}$ Junction to Case	$R_{\theta JA}$ Junction to Ambient	Unit
Thermal Resistance	Each Die	151	250	°C/W
	Effective, 4 Die	52	139	°C/W
Coupling Factors	Q1-Q4 or Q2-Q3	34	70	%
	Q1-Q2 or Q3-Q4	2.0	26	%

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

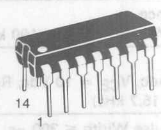
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	MPQ3798 MPQ3799	$V_{(BR)CEO}$	40 60	— —	— —	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0)		I_{CBO}	—	—	10	nAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)		I_{EBO}	—	—	20	nAdc
ON CHARACTERISTICS(2)						
DC Current Gain		h_{FE}			—	—
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc)	MPQ3798 MPQ3799		100 225	— —	—	
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	MPQ3798 MPQ3799		150 300	— —	— —	
(I_C = 500 μAdc, V_{CE} = 5.0 Vdc)	MPQ3798 MPQ3799		150 300	— —	— —	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	MPQ3798 MPQ3799		125 250	— —	— —	
Collector-Emitter Saturation Voltage (I_C = 100 μAdc, I_B = 10 μAdc) (I_C = 1.0 mAdc, I_B = 100 μAdc)		$V_{CE(sat)}$	— —	0.12 0.07	0.2 0.25	Vdc
Base-Emitter Saturation Voltage (I_C = 100 μAdc, I_B = 10 μAdc) (I_C = 1.0 mAdc, I_B = 100 μAdc)		$V_{BE(sat)}$	— —	0.62 0.68	0.7 0.8	Vdc

Characteristic		Symbol	Min	Typ	Max	Unit
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)		f_T	60	250	—	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz)		C_{obo}	—	2.1	4.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)		C_{ibo}	—	5.5	8.0	pF
Noise Figure (I_C = 100 μAdc, V_{CE} = 10 Vdc, R_S = 3.0 kohms, f = 10 Hz to 15.7 kHz)	MPQ3798	NF	—	2.5	—	dB
	MPQ3799		—	1.5	—	

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MPQ3904

CASE 646-06, STYLE 1
TO-116



QUAD AMPLIFIER/SWITCHING TRANSISTOR

NPN SILICON

Refer to 2N3904 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
		Each Transistor	Four Transistors Equal Power	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	 500 4.0	 900 7.2	 mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	 825 6.7	 2.4 19.2	 Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic		Junction to Case	Junction to Ambient	Unit
Thermal Resistance	Each Die Effective, 4 Die	151 52	250 139	°C/W °C/W
Coupling Factors	Q1-Q4 or Q2-Q3 Q1-Q2 or Q3-Q4	34 2.0	70 26	% %

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 40 Vdc, I_E = 0)	I_{CBO}	—	—	50	nAdc
Emitter Cutoff Current (V_{BE} = 40 Vdc, I_C = 0)	I_{EBO}	—	—	50	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc) (I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	h_{FE}	 30 50 75	 90 160 200	 — — —	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{CE(sat)}$	—	0.1	0.2	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{BE(sat)}$	—	0.65	0.85	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	250	300	—	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 140 kHz)	C_{obo}	—	2.0	4.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 140 kHz)	C_{ibo}	—	4.0	8.0	pF
SWITCHING CHARACTERISTICS					
Turn-On Time (I_C = 10 mAdc, V_{BE} = 0.5 Vdc, I_{B1} = 1.0 mAdc)	t_{on}	—	37	—	ns
Turn-Off Time (I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)	t_{off}	—	136	—	ns

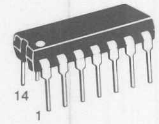
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CBO}	40		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
		Each Transistor	Four Transistors Equal Power	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	 500 4.0	 900 7.2	 mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	 825 6.7	 2.4 19.2	 Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

MPQ3906

CASE 646-06, STYLE 1
TO-116



QUAD
AMPLIFIER/SWITCH TRANSISTOR

PNP SILICON

5

Refer to 2N3906 for graphs.

THERMAL CHARACTERISTICS

Characteristic		Junction to Case	Junction to Ambient	Unit
Thermal Resistance	Each Die Effective, 4 Die	151 52	250 139	°C/W °C/W
Coupling Factors	Q1-Q4 or Q2-Q3 Q1-Q2 or Q3-Q4	34 2.0	70 26	% %

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	—	—	50	nAdc
Emitter Cutoff Current (V_{BE} = 4.0 Vdc, I_C = 0)	I_{EBO}	—	—	50	nAdc
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc) (I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc) (I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	h_{FE}	 40 60 75	 160 180 200	 — — —	—
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{CE(sat)}$	—	0.1	0.25	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{BE(sat)}$	—	0.65	0.85	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	200	250	—	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 140 kHz)	C_{obo}	—	3.3	4.5	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 140 kHz)	C_{ibo}	—	4.8	10	pF
SWITCHING CHARACTERISTICS					
Turn-On Time (I_C = 10 mAdc, $V_{BE(off)}$ = 0.5 Vdc, I_{B1} = 1.0 mAdc)	t_{on}	—	43	—	ns
Turn-Off Time (I_C = 10 mAdc, I_{B1} = I_{B2} = 1.0 mAdc)	t_{off}	—	155	—	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

5

FIGURE 1 — DELAY AND RISE TIME EQUIVALENT TEST CIRCUIT

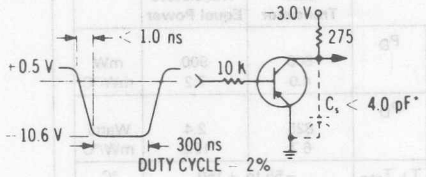
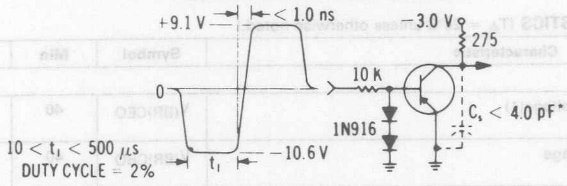


FIGURE 2 — STORAGE AND FALL TIME EQUIVALENT TEST CIRCUIT



*Total shunt capacitance of test jig and connectors

Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
		Each Transistor	**Four Transistors Equal Power**	
Total Device Dissipation @ T_A = 25°C(1) MPQ6001, MPQ6002, MPQ6501, MPQ6502	P_D	0.65	1.25	Watts
Derate above 25°C MPQ6001, MPQ6002, MPQ6501, MPQ6502		5.18	10	mW/°C
Total Device Dissipation @ T_C = 25°C MPQ6001, MPQ6002, MPQ6501, MPQ6502	P_D	1.0	3.0	Watts
Derate above 25°C MPQ6001, MPQ6002, MPQ6501, MPQ6502		8.0	24	mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

MPQ6002

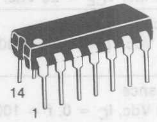
STYLE 1

MPQ6501

MPQ6502

STYLE 2

CASE 646-06



QUAD COMPLEMENTARY PAIR TRANSISTOR

PNP/NPN SILICON

THERMAL CHARACTERISTICS

Characteristic		Junction to Case	Junction to Ambient	Unit
Thermal Resistance		125	193	°C/W
Each Die	MPQ6001, MPQ6002, MPQ6501, MPQ6502			
Effective, 4 Die	MPQ6001, MPQ6002, MPQ6501, MPQ6502	41.6	100	
Coupling Factors		30	60	%
	MPQ6001, MPQ6002	30	60	
Q1-Q4 or Q2-Q3	MPQ6501, MPQ6502	30	60	
		30	60	
	MPQ6001, MPQ6002			
Q1-Q2 or Q3-Q4	MPQ6501, MPQ6502	20	24	
		20	24	
		20	24	
		2.0	24	

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)		$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0)		I_{CBO}	—	—	30	nAdc
Emitter Cutoff Current (V_{EB} = 3.0 Vdc, I_C = 0)		I_{EBO}	—	—	30	nAdc
ON CHARACTERISTICS						
DC Current Gain(2)		h_{FE}				—
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)	MPQ6001, MPQ6501		25	—	—	
	MPQ6002, MPQ6502		50	—	—	
(I_C = 10 mAdc, V_{CE} = 10 Vdc)	MPQ6001, MPQ6501		35	—	—	
	MPQ6002, MPQ6502		75	—	—	
(I_C = 150 mAdc, V_{CE} = 10 Vdc)	MPQ6001, MPQ6501		40	—	—	
	MPQ6002, MPQ6502		100	—	—	
(I_C = 300 mAdc, V_{CE} = 10 Vdc)	MPQ6001, MPQ6501		20	—	—	
	MPQ6002, MPQ6502		30	—	—	

5

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Collector-Emitter Saturation Voltage(2)	$V_{CE(sat)}$				Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)		—	—	0.4	
(I_C = 300 mAdc, I_B = 30 mAdc)		—	—	1.4	
Base-Emitter Saturation Voltage(2)	$V_{BE(sat)}$				Vdc
(I_C = 150 mAdc, I_B = 15 mAdc)		—	—	1.3	
(I_C = 300 mAdc, I_B = 30 mAdc)		—	—	2.0	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 50 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	200	350		MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{obo}				pF
PNP		—	6.0	8.0	
NPN		—	4.5	8.0	
Input Capacitance (V_{EB} = 2.0 Vdc, I_C = 0, f = 100 kHz)	C_{ibo}				pF
PNP		—	20	30	
NPN		—	17	30	
SWITCHING CHARACTERISTICS					
Turn-On Time (V_{CC} = 30 Vdc, V_{BE} = 0.5 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc, Figure 1)	t_{on}	—	30	—	ns
Turn-Off Time (V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_{off}	—	225	—	ns

(1) Second Breakdown occurs at power levels greater than 3 times the power dissipation rating.
(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

5

NPN DATA

FIGURE 1 — NORMALIZED DC CURRENT GAIN

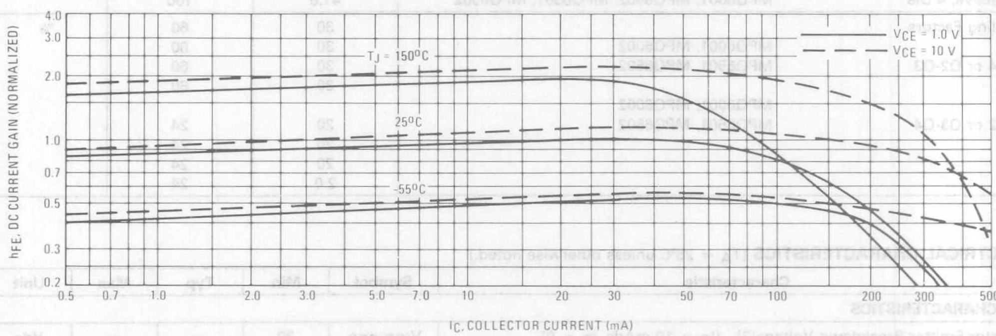


FIGURE 2 — "ON" VOLTAGES

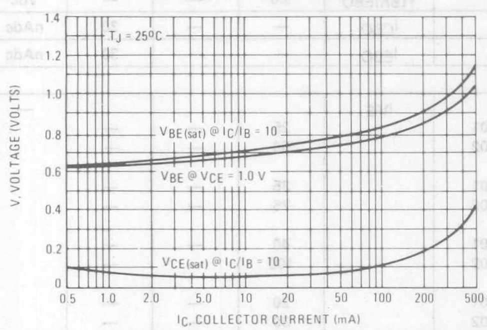
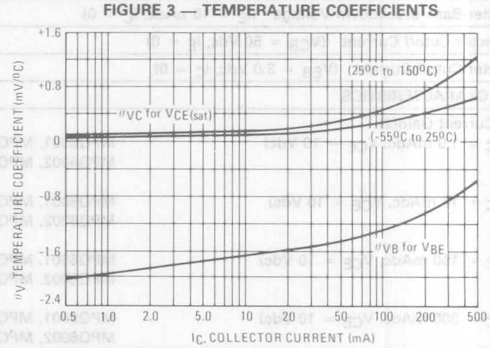


FIGURE 3 — TEMPERATURE COEFFICIENTS



NOISE FIGURE
(V_{CE} = 10 Vdc, T_A = 25°C)

FIGURE 4 — FREQUENCY EFFECTS

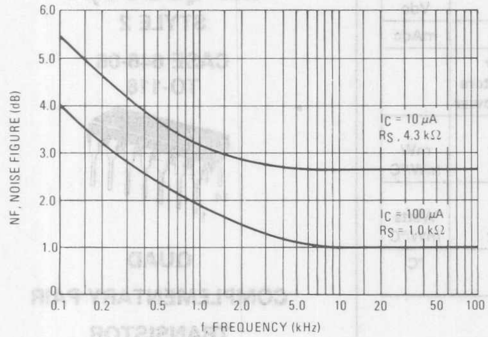
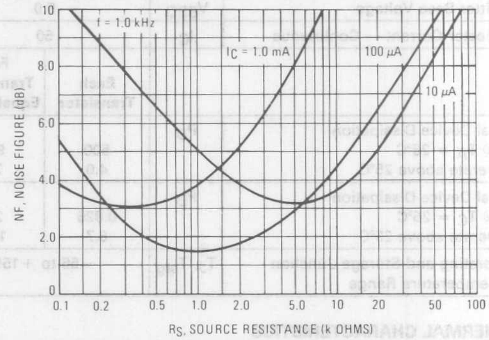


FIGURE 5 — SOURCE RESISTANCE EFFECTS

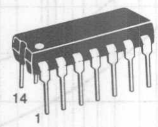


5

MPQ6100,A
STYLE 1

MPQ6600,A
STYLE 2

CASE 646-06
TO-116



QUAD COMPLEMENTARY PAIR TRANSISTOR

PNP/NPN SILICON

Refer to MHQ2483 for NPN Curves.

Refer to MHQ3798 for PNP Curves.

MAXIMUM RATINGS

Rating	Symbol	MPQ6100 MPQ6600	MPQ6100A MPQ6600A	Unit
Collector-Emitter Voltage	V_{CEO}	40	45	Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
		Each Transistor	Four Transistors Equal Power	
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	 500 4.0	 900 7.2	 mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	 0.825 6.7	 2.4 19.2	 Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic		Junction to Case	Junction to Ambient	Unit
Thermal Resistance(1)	Each Die	151	250	°C/W
	Effective, 4 Die	52	139	°C/W
Coupling Factors	Q1-Q4 or Q2-Q3	34	70	%
	Q1-Q2 or Q3-Q4	2.0	26	%

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	 MPQ6100,6600 MPQ6100A,6600A	$V_{(BR)CEO}$	 40 45	 — —	 — —	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0)		I_{CBO}	—	—	10	nAdc
ON CHARACTERISTICS(2)						
DC Current Gain (I_C = 100 μAdc, V_{CE} = 5.0 Vdc)	 MPQ6100,6600 MPQ6100A,6600A	h_{FE}	 50 100	 — —	 — —	—
(I_C = 500 μAdc, V_{CE} = 5.0 Vdc)	MPQ6100,6600 MPQ6100A,6600A		75 150	— —	— —	
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	MPQ6100,6600 MPQ6100A,6600A		75 150	— —	— —	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	MPQ6100,6600 MPQ6100A,6600A		60 125	— —	— —	
Collector-Emitter Saturation Voltage (I_C = 1.0 mAdc, I_B = 100 μAdc)		$V_{CE(sat)}$	—	—	0.25	Vdc
Base-Emitter Saturation Voltage (I_C = 1.0 mAdc, I_B = 100 μAdc)		$V_{BE(sat)}$	—	—	0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product (I_C = 500 μAdc, V_{CE} = 5.0 Vdc, f = 20 MHz)		f_T	50	—	—	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 100 kHz)	 PNP NPN	C_{obo}	 — —	 1.2 1.8	 4.0 4.0	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

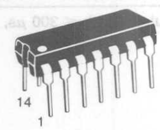
Characteristic		Symbol	Min	Typ	Max	Unit
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)	PNP NPN	C_{ibo}	— —	— —	8.0 8.0	pF
Noise Figure (I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 kohms, f = 10 Hz to 15.7 kHz, BW = 10 kHz)		NF	—	4.0	—	dB

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

5

MPQ6426
MPQ6427

CASE 646-06, STYLE 1
TO-116



QUAD
DARLINGTON TRANSISTOR

NPN SILICON

5

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage MPQ6426 MPQ6427	V_{CEO}	30 40		Vdc
Collector-Base Voltage MPQ6426 MPQ6427	V_{CBO}	40 50		Vdc
Emitter-Base Voltage	V_{EBO}	12		Vdc
Collector Current — Continuous	I_C	500		mAdc
		Each Die	Four Die Equal Power	
Total Device Dissipation @ T_A = 25°C(1) Derate above 25°C	P_D	500 4.0	900 7.2	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	825 6.7	2400 19.2	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

(1) Second Breakdown occurs at power levels greater than 3 times the power dissipation rating.

THERMAL CHARACTERISTICS

Characteristic		Junction to Case	Junction to Ambient	Unit
Thermal Resistance	Each Die	151	250	°C/W
	Effective, 4 Die	52	139	°C/W
Coupling Factors	Q1-Q4 or Q2-Q3	34	70	%
	Q1-Q2 or Q3-Q4	2.0	26	%

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0) MPQ6426 MPQ6427	$V_{(BR)CEO}$	30 40	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0) MPQ6426 MPQ6427	$V_{(BR)CBO}$	40 50	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	12	—	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	—	100	nAdc
Emitter Cutoff Current (V_{BE} = 10 Vdc, I_C = 0)	I_{EBO}	—	100	nAdc
ON CHARACTERISTICS(2)				
DC Current Gain (I_C = 10 mAdc, V_{CE} = 5.0 Vdc) (I_C = 100 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}	5000 10,000	— —	—
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 0.1 mAdc)	$V_{CE(sat)}$	—	1.5	Vdc
Base-Emitter On Voltage (I_C = 100 mAdc, V_{CE} = 5.0 Vdc)	$V_{BE(on)}$	—	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)	f_T	125	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	8.0	pF
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 100 kHz)	C_{ibo}	—	15	pF

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

NOISE CHARACTERISTICS
(V_{CE} = 5.0 Vdc, T_A = 25°C)

FIGURE 1 – NOISE VOLTAGE

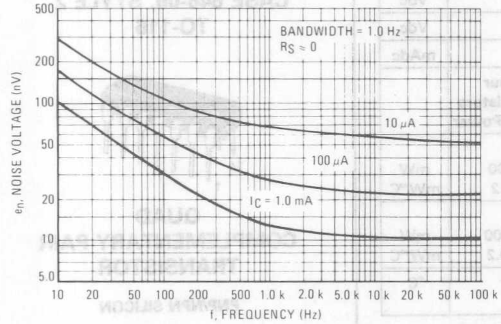


FIGURE 2 – NOISE CURRENT

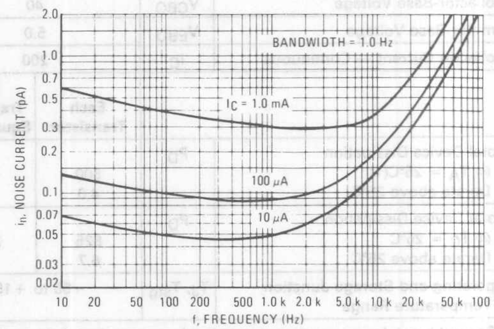


FIGURE 3 – TOTAL WIDEBAND NOISE VOLTAGE

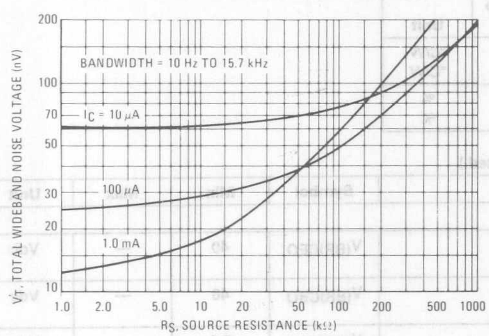
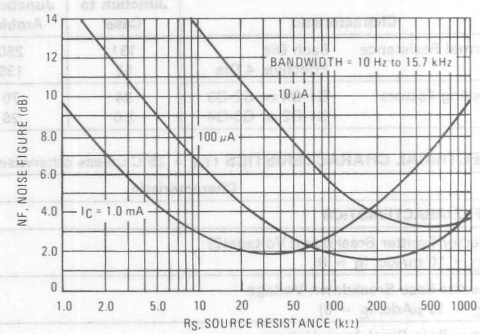


FIGURE 4 – WIDEBAND NOISE FIGURE



DYNAMIC CHARACTERISTICS

FIGURE 5 – CAPACITANCE

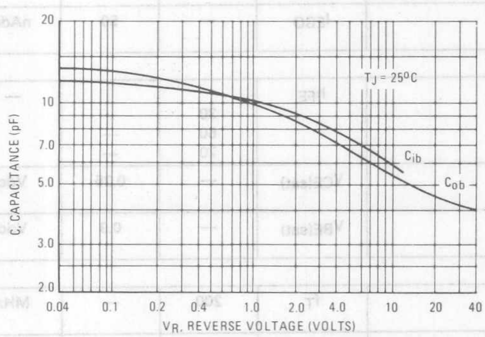
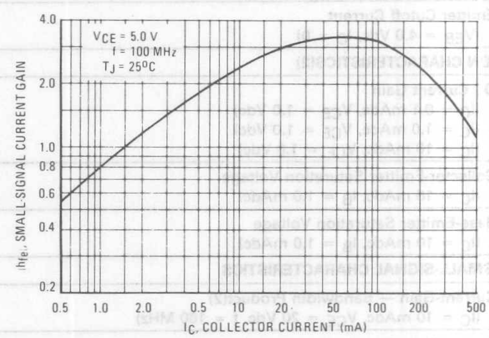


FIGURE 6 – HIGH FREQUENCY CURRENT GAIN

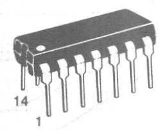


MPQ6501, MPQ6502 For Specifications, See MPQ6001 Data

MPQ6600,A For Specifications, See MPQ6100,A Data.

MPQ6700

CASE 646-06, STYLE 2
TO-116



QUAD COMPLEMENTARY PAIR TRANSISTOR

PNP/NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	40		Vdc
Collector-Base Voltage	V_{CBO}	40		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
		Each Transistor	Four Transistors Equal Power	
Total Device Dissipation @ $T_A = 25°C$(1) Derate above 25°C	P_D	500 4.0	900 7.2	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	825 6.7	2400 19.2	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

(1) Second breakdown occurs at power levels greater than 3 times the power dissipation rating.

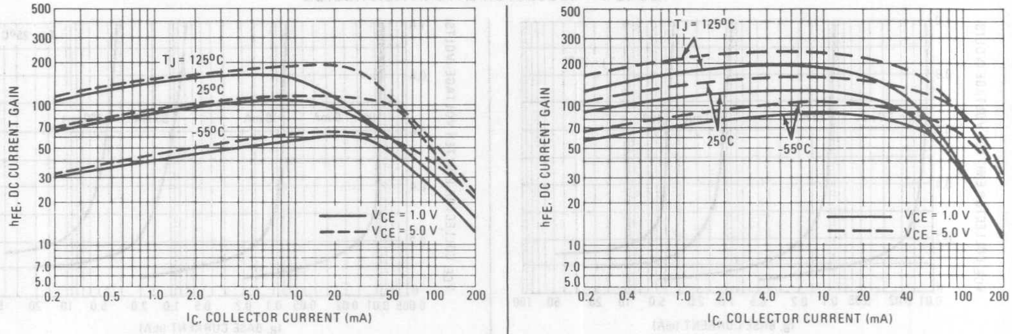
THERMAL CHARACTERISTICS

Characteristic		Junction to Case	Junction to Ambient	Unit
Thermal Resistance	Each Die Effective, 4 Die	151 52	250 139	°C/W °C/W
Coupling Factors	Q1-Q4 or Q2-Q3 Q1-Q2 or Q3-Q4	34 2.0	70 26	% %

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	40	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 30$ Vdc, $I_E = 0$)	I_{CBO}	—	50	nAdc
Emitter Cutoff Current ($V_{EB} = 4.0$ Vdc, $I_C = 0$)	I_{EBO}	—	50	nAdc
ON CHARACTERISTICS(2)				
DC Current Gain ($I_C = 0.1$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	 30 50 70	 — — —	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	0.25	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	—	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product(2) ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)	f_T	200	—	MHz
Output Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	4.5	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz) PNP NPN	C_{ibo}	 — —	 10 8.0	pF

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.



5

FIGURE 2 – "ON" VOLTAGE

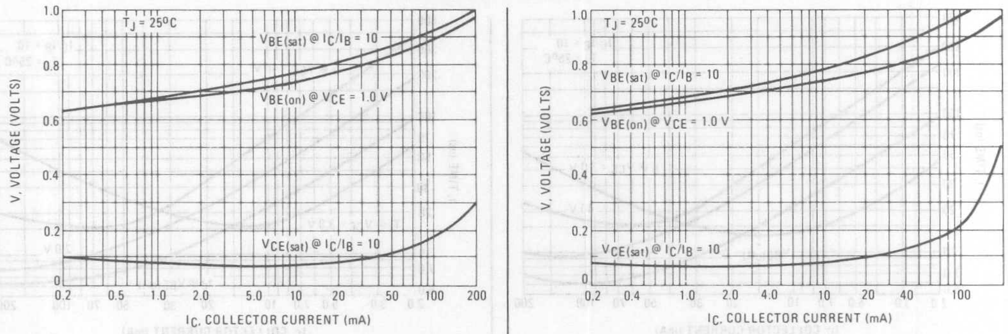
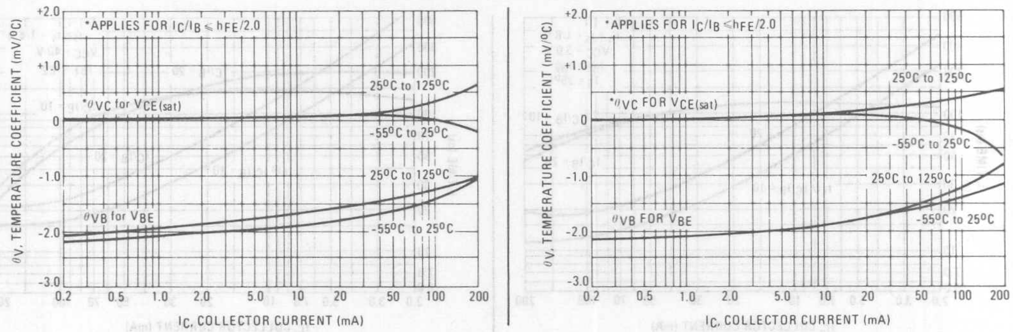


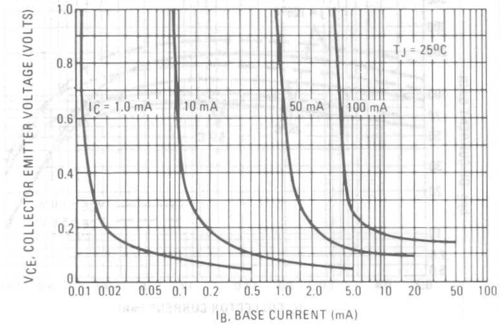
FIGURE 3 – TEMPERATURE COEFFICIENTS



5

NPN | PNP

FIGURE 4 – COLLECTOR SATURATION REGION



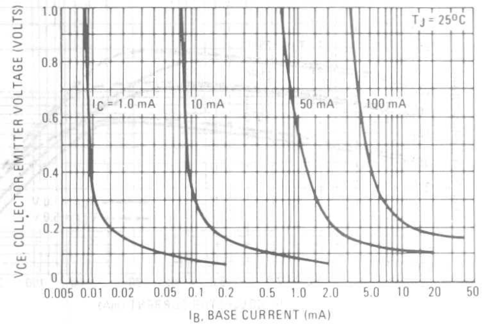
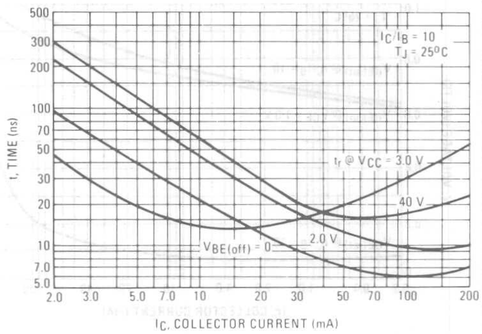


FIGURE 5 – TURN-ON TIME



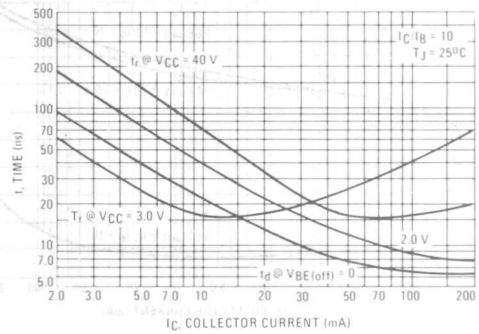
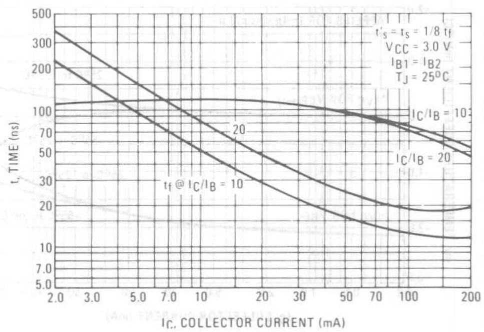
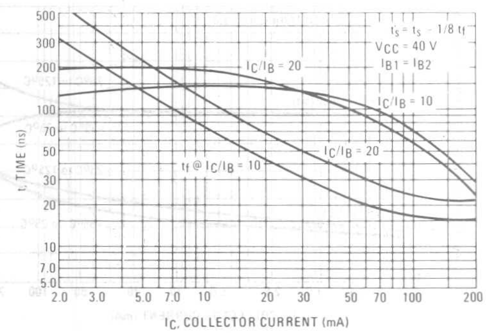


FIGURE 6 – TURN-OFF TIME





NPN | PNP

FIGURE 7 – CURRENT-GAIN – BANDWIDTH PRODUCT

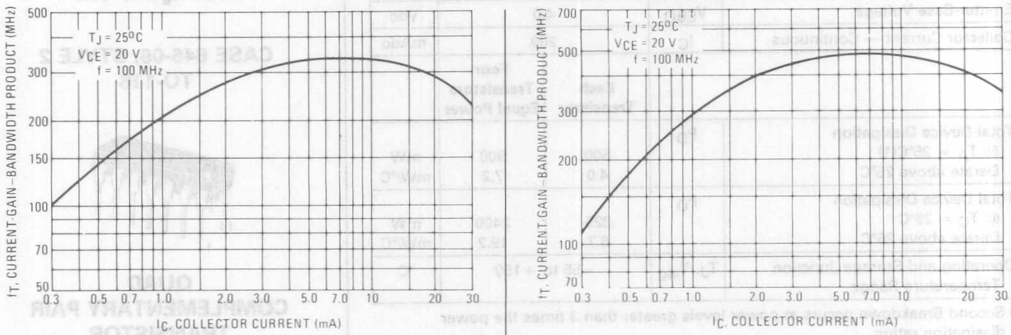
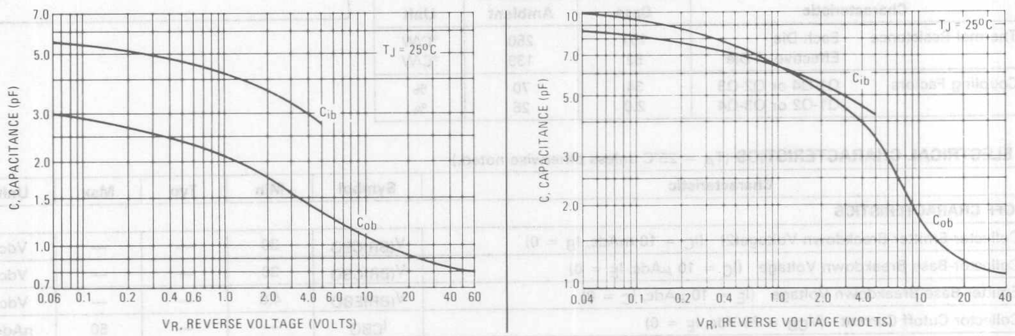


FIGURE 8 – CAPACITANCE



5

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	30		Vdc
Collector-Base Voltage	V_{CBO}	30		Vdc
Emitter-Base Voltage	V_{EBO}	4.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
		Each Transistor	Four Transistors Equal Power	
Total Device Dissipation @ $T_A = 25°C$(1) Derate above 25°C	P_D	 500 4.0	 900 7.2	 mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	 825 6.7	 2400 19.2	 mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

(1) Second Breakdown occurs at power levels greater than 3 times the power dissipation rating.

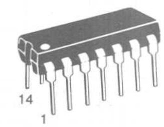
5

THERMAL CHARACTERISTICS

Characteristic		Junction to Case	Junction to Ambient	Unit
Thermal Resistance	Each Die Effective, 4 Die	151 52	250 139	°C/W °C/W
Coupling Factors	Q1-Q4 or Q2-Q3 Q1-Q2 or Q3-Q4	34 2.0	70 26	% %

MPQ6842

CASE 646-06, STYLE 2
TO-116



QUAD COMPLEMENTARY PAIR TRANSISTOR

PNP/NPN SILICON

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) ($I_C = 10$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μAdc, $I_E = 0$)	$V_{(BR)CBO}$	30	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μAdc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$)	I_{CBO}	—	—	50	nAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	—	50	nAdc
ON CHARACTERISTICS(2)					
DC Current Gain ($I_C = 0.5$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 1.0$ mAdc, $V_{CE} = 1.0$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	30 50 70	— — —	— — —	—
Collector-Emitter Saturation Voltage ($I_C = 0.5$ mAdc, $I_B = 0.05$ mAdc, 0°C ≤ T ≤ 70°C)	$V_{CE(sat)}$	—	0.05	0.15	Vdc
Base-Emitter Saturation Voltage ($I_C = 0.5$ mAdc, $I_B = 0.05$ mAdc)	$V_{BE(sat)}$	—	0.65	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)	f_T	200	350	—	MHz
Output Capacitance ($V_{CB} = 5.0$ Vdc, $I_E = 0$, f = 100 kHz)	C_{obo}	—	3.0	4.5	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, f = 100 kHz) PNP NPN	C_{ibo}	 — —	 5.0 4.0	 10 8.0	pF
SWITCHING CHARACTERISTICS ($T_A = 25°C$, $V_{CC} = 5.0$ Vdc)					
Propagation Delay Time (50% Points TP1 to TP3) (50% Points TP2 to TP4)	 t_{PLH} t_{PHL}	 — —	 15 6.0	 25 15	ns
Rise Time (0.3 V to 4.7 V, TP3 or TP4)	t_r	5.0	25	35	ns
Fall Time (4.7 V to 0.3 V, TP3 or TP4)	t_f	5.0	10	20	ns

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

NPN **PNP**

FIGURE 1 – DC CURRENT GAIN

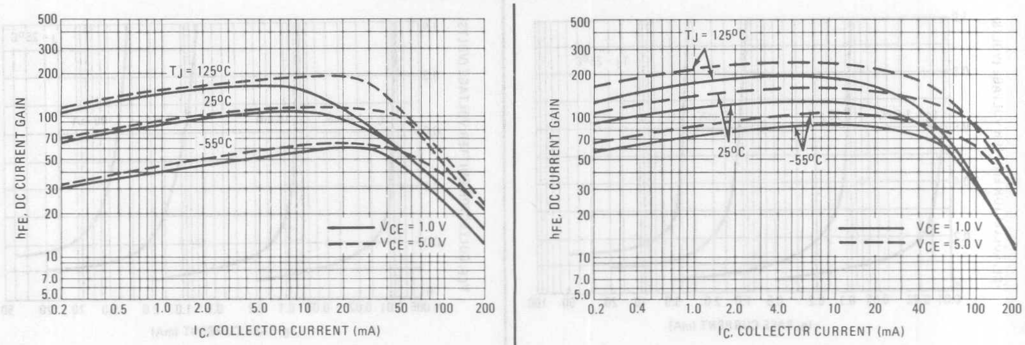


FIGURE 2 – "ON" VOLTAGE

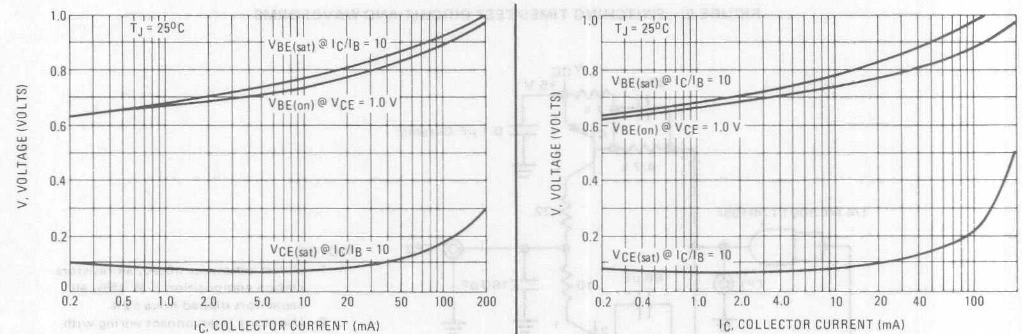


FIGURE 3 – TEMPERATURE COEFFICIENTS

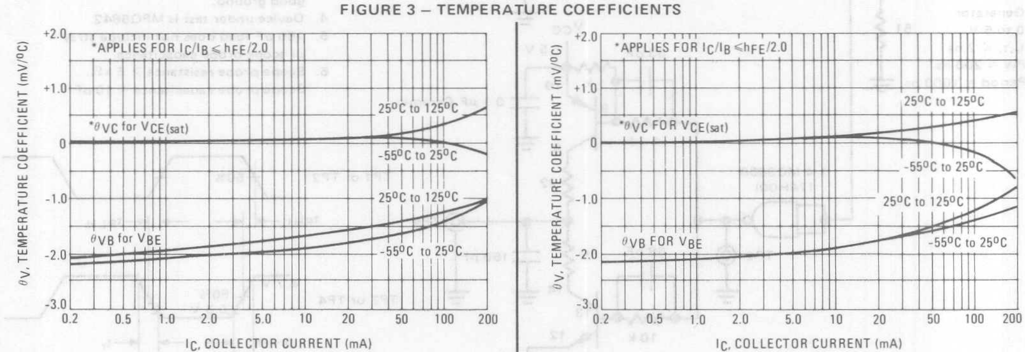


FIGURE 4 – COLLECTOR SATURATION REGION

NPN   PNP

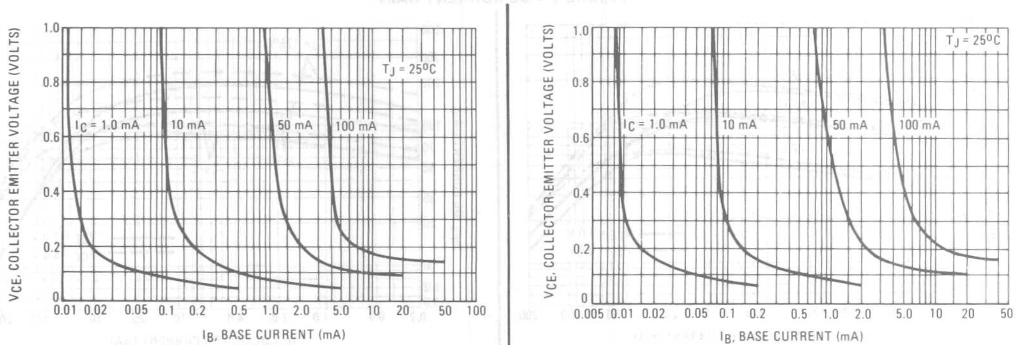
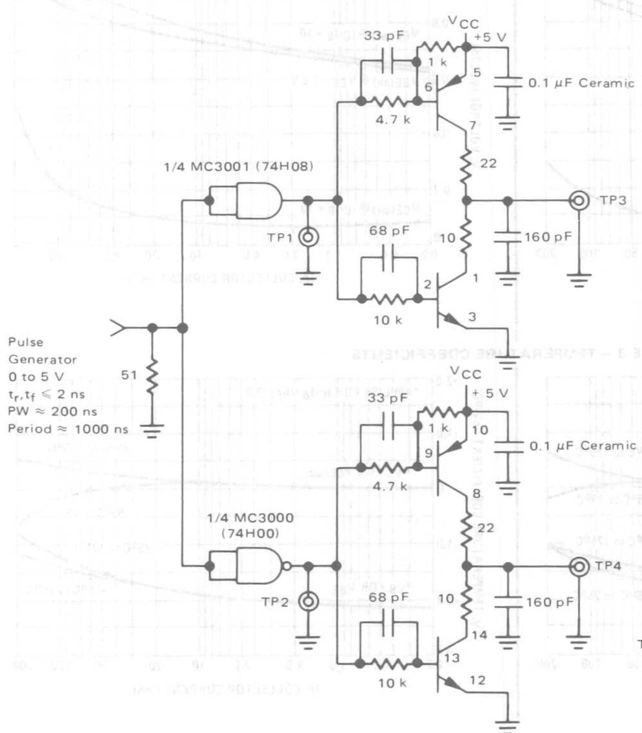
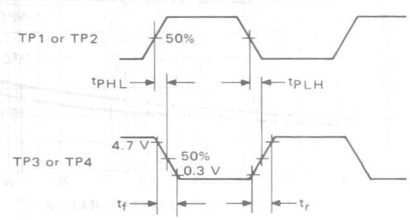


FIGURE 5 – SWITCHING TIMES TEST CIRCUIT AND WAVEFORMS



NOTES:

1. Unless otherwise noted, all resistors carbon composition ¼ W ±5%, all capacitors dipped mica ±2%.
2. Use short interconnect wiring with good power and ground busses.
3. TP1 thru TP4 are coaxial connectors to accept scope probe tip and provide a good ground.
4. Device under test is MPQ6842.
5. 160 pF load does not include stray or scope probe capacitance.
6. Scope probe resistance > 5 kΩ. Scope probe capacitance < 10 pF.



MAXIMUM RATINGS

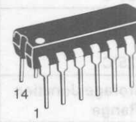
Rating	Symbol	MPQ7041	MPQ7042	MPQ7043	Unit
Collector-Emitter Voltage	V_{CEO}	150	200	250	Vdc
Collector-Base Voltage	V_{CBO}	150	200	250	Vdc
Emitter-Base Voltage	V_{EBO}		5.0		Vdc
Collector Current — Continuous	I_C		500		mAdc
		Each Die	Four Die Equal Power		
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	750 5.98	1700 13.6		mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.25 10	3.2 25.6		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic		Junction to Case	Junction to Ambient	Unit
Thermal Resistance	Each Die	100	167	°C/W
	Effective, 4 Die	39	73.5	°C/W
Coupling Factors	Q1-Q4 or Q2-Q3	46	56	%
	Q1-Q2 or Q3-Q4	5.0	10	%

MPQ7041
MPQ7042
MPQ7043

CASE 646-06, STYLE 1
TO-116



QUAD AMPLIFIER TRANSISTOR

NPN SILICON

Refer to MPQ7051 for graphs.

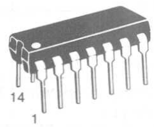
5

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_B = 0$)	MPQ7041 MPQ7042 MPQ7043	$V_{(BR)CEO}$	150 200 250	— — —	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu$Adc, $I_E = 0$)	MPQ7041 MPQ7042 MPQ7043	$V_{(BR)CBO}$	150 200 250	— — —	— — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\ \mu$Adc, $I_C = 0$)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 120$ Vdc, $I_E = 0$) ($V_{CB} = 150$ Vdc, $I_E = 0$) ($V_{CB} = 180$ Vdc, $I_E = 0$)	MPQ7041 MPQ7042 MPQ7043	I_{CBO}	— — —	— — —	100 100 100	nAdc
ON CHARACTERISTICS						
DC Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc) ($I_C = 30$ mAdc, $V_{CE} = 10$ Vdc)		h_{FE}	25 40 40	45 60 80	— — —	—
Collector-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)		$V_{CE(sat)}$	—	0.3	0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 20$ mAdc, $I_B = 2.0$ mAdc)		$V_{BE(sat)}$	—	0.7	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)		f_T	50	80	—	MHz
Output Capacitance ($V_{CB} = 20$ Vdc, $I_E = 0$, f = 1.0 MHz)		C_{obo}	—	2.5	5.0	pF
Input Capacitance ($V_{EB} = 3.0$ Vdc, $I_C = 0$, f = 1.0 MHz)		C_{ibo}	—	40	50	pF

MPQ7092
MPQ7093

CASE 646-06, STYLE 1
TO-116



QUAD AMPLIFIER TRANSISTOR

PNP SILICON

Refer to MPQ7051 for graphs.

Collector-Base Voltage	V_{CBO}	150	200	250	Vdc
Emitter-Base Voltage	V_{EBO}	5.0			Vdc
Collector Current — Continuous	I_C	500			mAdc
		Each Die	**Four Die Equal Power**		
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	750 5.98	1700 13.6		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.25 10	3.2 25.6		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150			°C

THERMAL CHARACTERISTICS

Characteristic		Junction to Case	Junction to Ambient	Unit
Thermal Resistance	Each Die Effective, 4 Die	100 39	167 73.5	°C/W °C/W
Coupling Factors	Q1-Q4 or Q2-Q3 Q1-Q2 or Q3-Q4	46 5.0	56 10	% %

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	MPQ7091 MPQ7092 MPQ7093	$V_{(BR)CEO}$	150 200 250	— — —	— — —	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	MPQ7091 MPQ7092 MPQ7093	$V_{(BR)CBO}$	150 200 250	— — —	— —	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 120 Vdc, I_E = 0) (V_{CB} = 150 Vdc, I_E = 0) (V_{CB} = 180 Vdc, I_E = 0)	MPQ7091 MPQ7092 MPQ7093	I_{CBO}	— — —	— — —	250 250 250	nAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)		I_{EBO}	—	—	100	nAdc
ON CHARACTERISTICS						
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc) (I_C = 30 mAdc, V_{CE} = 10 Vdc)		h_{FE}	25 35 25	40 55 50	— — —	—
Collector-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)		$V_{CE(sat)}$	—	0.3	0.5	Vdc
Base-Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 2.0 mAdc)		$V_{BE(sat)}$	—	0.7	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)		f_T	50	70	—	MHz
Output Capacitance (V_{CB} = 20 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	3.0	5.0	pF
Input Capacitance (V_{EB} = 3.0 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	60	75	pF

MQ982 For Specifications, See MD982,F Data.

MQ1120 For Specifications, See MD1120F Data.

MQ2218,A/MQ2219,A For Specifications, See MD2218,A,F,AF Data.

MQ2369 For Specifications, See MD2369,A,B Data.

MQ2904/MQ2905A For Specifications, See MD2904,A,F,AF Data.

MQ3251 For Specifications, See MD3250,A,F,AF Data.

MQ3467 For Specifications, See MD3467 Data.

MQ3725 For Specifications, See MD3725,F Data.

MQ3762 For Specifications, See MD3762,F Data.

MQ6001/MQ6002 For Specifications, See MD6001,F Data.

MQ7001 For Specifications, See MD7001,F Data.

MQ7003 For Specifications, See MD7003,A,B,AF Data.

MQ7007 For Specifications, See MD7007,A,B,F,BF Data.

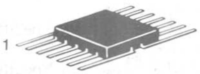
MQ7021 For Specifications, See MD7021,F Data.

5

MQ1129

CASE 607-04, STYLE 1

14



1

DUAL AMPLIFIER TRANSISTOR

NPN SILICON

5

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	30		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	500		mAdc
		One Die	All Die Equal Power	
Total Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	400 2.28	600 3.42	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	0.9 5.13	3.6 20.5	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	One Die	All Die Equal Power	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	195	48.8	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	438	292	°C/W
		Junction to Ambient	Junction to Case	
Coupling Factors MQ1129 (Q1-Q2) (Q1-Q3 or Q1-Q4)		 57 55	 0 0	%

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	60	—	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0) (V_{CB} = 50 Vdc, I_E = 0, T_A = 150°C)	I_{CBO}	 — —	 — —	 10 10	 nAdc μAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)	I_{EBO}	—	—	10	nAdc

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
DC Current Gain(2)	h_{FE}				—
(I_C = 10 μAdc, V_{CE} = 10 Vdc)		60	—	—	
(I_C = 100 μAdc, V_{CE} = 10 Vdc)		100	—	300	
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)		100	120	—	
(I_C = 10 mAdc, V_{CE} = 10 Vdc)		100	140	—	
Collector-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{CE(sat)}$	—	0.09	0.1	Vdc
Base-Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{BE(sat)}$	—	0.7	0.85	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(2) (I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	200	250	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 100 kHz)	C_{obo}	—	3.5	8.0	pF
MATCHING CHARACTERISTICS (MD1129, MD1129F)					
DC Current Gain Ratio(3)	h_{FE1}/h_{FE2}				—
(I_C = 100 μAdc, V_{CE} = 10 Vdc)		0.9	—	1.0	
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)		0.9	—	1.0	
Base-Emitter Voltage Differential	$\|V_{BE1}-V_{BE2}\|$				mVdc
(I_C = 100 μAdc, V_{CE} = 10 Vdc)		—	—	5.0	
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc)		—	—	5.0	
Base-Emitter Voltage Differential Change Due to Temperature	$\Delta(V_{BE1}-V_{BE2})$				mVdc
(I_C = 100 μAdc, V_{CE} = 10 Vdc, T_A = −55 to +25°C)		—	—	0.8	
(I_C = 100 μAdc, V_{CE} = 10 Vdc, T_A = +25 to +125°C)		—	—	1.0	

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.
(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(3) The lowest h_{FE} reading is taken as h_{FE1} for this ratio.

5

5

Field-Effect Transistors

6

The data sheets on the following pages are designed to emphasize those FET's that by virtue of widespread industry use, ease of manufacture, and consequently low relative cost, merit first consideration for new equipment design. Package options from low-cost plastic to metal packages are available.

CAUTION:

Static electricity is a surface phenomenon which most commonly occurs when two dissimilar materials come into contact and then separate. Electro Static Discharge (ESD) damage of semiconductor components by operating personnel is quickly becoming a very prominent and significant problem. From simple bipolar designs to sensitive MOSFET structures, ESD has its unforgiving effect of degradation or destruction.

Motorola believes it is important to extend an emphasizing note of cautiousness when handling and testing *ANY* FET product. Precautions include, but are not limited to, the implementation of static safe workstations and proper handling techniques (see below). Additionally, it is very important to keep FET devices in their antistatic shipping containers and away from any static-generating materials.

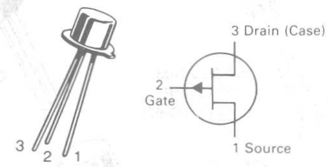
HANDLING CONSIDERATIONS:

MOS Field-Effect Transistors, due to their extremely high input resistance, are subject to potential damage by the accumulation of excess static charge. To avoid possible damage to the devices while handling, testing, or in actual operation, the following procedure should be followed:

1. The leads of the devices should remain wrapped in the shorting spring except when being tested or in actual operation to avoid the build-up of static charge.
2. Avoid unnecessary handling; when handled, the devices should be picked up by the *can* instead of the leads.
3. The devices should not be inserted or removed from circuits with the power on as transient voltages may cause permanent damage to the devices.

2N2843
2N2844

CASE 22-03, STYLE 12
TO-18 (TO-206AA)



JFET
GENERAL PURPOSE

P-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage	V_{GS}	30	Vdc
Drain Current	I_D	50	mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	300 1.7	mW mW/°C
Storage Temperature Range	T_{stg}	−60 to +200°C	°C

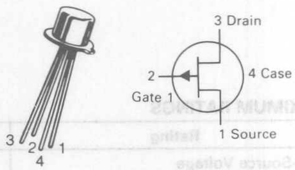
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = 1.0\ \mu A$)		$V_{(BR)GSS}$	30	—	Vdc
Gate Reverse Current ($V_{GS} = 5.0$ V)		I_{GSS}	—	10	nA
Gate Source Cutoff Voltage ($V_{DS} = -5.0$ V, $I_D = -1.0\ \mu A$)		$V_{GS(off)}$	—	1.7	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current ($V_{DS} = -5.0$ V)	 2N2843 2N2844	I_{DSS}*	 200 440	 1000 2200	μA
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance ($V_{DS} = -5.0$ V, f = 1.0 kHz)	 2N2843 2N2844	$\|y_{fs}\|$*	 540 1400	 — —	μmhos
Input Capacitance ($V_{DS} = -5.0$ V, $V_{GS} = 1.0$ V, f = 140 kHz)	 2N2843 2N2844	C_{iss}	 — —	 17 30	pF
FUNCTIONAL CHARACTERISTICS					
Noise Figure ($V_{DS} = -5.0$ V, f = 1.0 kHz, $R_G = 1.0$ meg)		NF	—	3.0	dB

*Pulse Width ≤ 630 ms, Duty Cycle = 10%.

2N3330

CASE 20-03, STYLE 5
TO-72 (TO-206AF)



JFET
AMPLIFIER

P-CHANNEL — DEPLETION

Refer to 2N5460 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V_{DG}	20	Vdc
Reverse Gate-Source Voltage	V_{GSR}	20	Vdc
Gate Current	I_G	10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.3 1.7	Watts mW/°C
Storage Temperature Range	T_{stg}	−65 to +200	°C

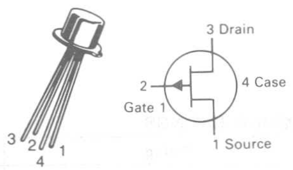
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage (I_G = 10 μAdc, V_{DS} = 0)	$V_{(BR)GSS}$	20	—	Vdc
Gate Reverse Current (V_{GS} = 10 Vdc, V_{DS} = 0) (V_{GS} = 10 Vdc, V_{DS} = 0, T_A = 150°C)	I_{GSS}	 — —	 10 10	 nAdc μAdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current(1) (V_{DS} = −10 Vdc, V_{GS} = 0)	I_{DSS}	2.0	6.0	mAdc
Gate-Source Voltage (V_{DG} = −15 Vdc, I_D = 10 μAdc)	V_{GS}	—	6.0	Vdc
Drain-Source Resistance (I_D = 100 μAdc, V_{GS} = 0)	r_{DS}	—	800	Ohms
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance(1) (V_{DS} = −10 Vdc, I_D = 2.0 mAdc, f = 1.0 kHz) (V_{DS} = −10 Vdc, I_D = 2.0 mAdc, f = 10 MHz)	$\|y_{fs}\|$	 1500 1350	 3000 	μmhos
Output Admittance (V_{DS} = −10 Vdc, I_D = 2.0 mAdc, f = 1.0 kHz)	$\|y_{os}\|$	—	40	μmhos
Reverse Transfer Conductance (V_{DS} = −10 Vdc, I_D = 2.0 mAdc, f = 1.0 kHz)	$\|y_{rs}\|$	—	0.1	μmhos
Input Conductance (V_{DS} = −10 Vdc, I_D = 2.0 mAdc, f = 1.0 kHz)	$\|y_{is}\|$	—	0.2	μmhos
Input Capacitance (V_{DS} = −10 Vdc, V_{GS} = 1.0 Vdc, f = 1.0 MHz)	C_{iss}	—	20	pF
FUNCTIONAL CHARACTERISTICS				
Noise Figure (V_{DS} = −5.0 Vdc, I_D = 1.0 mAdc, R_G = 1.0 Megohm, f = 1.0 kHz)	NF	—	3.0	dB

(1) Pulse Test: Pulse Width ≤ 630 ms, Duty Cycle ≤ 10%.

6

CASE 20-03, STYLE 5
TO-72 (TO-206AF)



JFET
LOW-FREQUENCY

P-CHANNEL — DEPLETION

Refer to 2N5460 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	Vdc
Drain-Gate Voltage	V_{DG}	20	Vdc
Gate-Source Voltage	V_{GS}	20	Vdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 1.7	mW mW/°C
Storage Temperature Range	T_{stg}	−65 to +200	°C

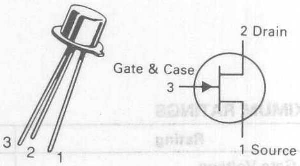
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage (I_G = 10 μA)	$V_{(BR)GSS}$	20	—	Vdc
Gate Reverse Current (V_{GS} = 10 V, V_{DS} = 0)	I_{GSS}	—	10	nA
Gate Source Cutoff Voltage (V_{DS} = −15 V, I_D = −10 μA)	$V_{GS(off)}$	—	8.0	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current (V_{DS} = −10 V, V_{GS} = 0 V)	I_{DSS}*	−5.0	−15.0	mA
Drain-Source Resistance (I_D = −100 μA, V_{GS} = 0)	r_{DS}	—	800	ohms
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance (V_{DS} = −10 V, I_D = −5.0 mA, f = 1.0 kHz)	$\|y_{fs}\|$*	2000	4000	μmhos
Output Admittance (V_{DS} = −10 V, I_D = −2.0 mA, f = 1.0 kHz)	$\|y_{os}\|$*	—	100	μmhos
Forward Transfer Admittance (V_{DS} = −10 V, I_D = −2.0 mA, f = 10 MHz)	y_{fs}*	1350	—	μmhos
Input Capacitance (V_{DS} = −10 V, V_{GS} = 1.0 V, f = 1.0 MHz)	C_{iss}	—	20	pF
FUNCTIONAL CHARACTERISTICS				
Noise Figure (V_{DS} = −5.0 V, I_D = −1.0 mA, R_G = 1.0 MΩ, f = 1.0 kHz)	NF	—	4.0	dB

*Pulse Width ≤ 300 μs, Duty Cycle ≤ 10%.

2N3437
2N3438

CASE 22-03, STYLE 4
TO-18 (TO-206AA)



JFET
LOW-FREQUENCY

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V_{DG}	50	Vdc
Gate-Source Voltage	V_{GS}	50	Vdc
Gate Current	I_G	10	mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	300 1.7	mW mW/°C
Storage Temperature Range	T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

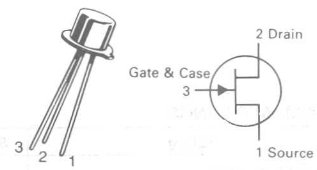
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = 1.0\ \mu A$)		$V_{(BR)GSS}$	50	—	Vdc
Gate Reverse Current ($V_{GS} = -30$ V)		I_{GSS}	—	0.5	nA
Gate Source Cutoff Voltage ($V_{DS} = 20$ V, $I_D = 1.0$ nA)	2N3437 2N3438	$V_{GS(off)}$	— —	5.0 2.5	Vdc
Gate Source Voltage ($V_{DS} = 20$ V, $I_D = 1.0\ \mu A$)	2N3437 2N3438	V_{GS}	— —	4.8 2.3	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current ($V_{DS} = 20$ V)	2N3437 2N3438	I_{DSS}*	0.8 0.2	4.0 1.0	mA
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance ($V_{DS} = 20$ V, f = 1.0 kHz)	2N3437 2N3438	$\lvert y_{fs} \rvert$	1500 800	6000 4500	μmhos
Output Admittance ($V_{DS} = 30$ V, f = 1.0 kHz)	2N3437 2N3438	$\lvert y_{os} \rvert$	— —	20 5.0	μmhos
Input Capacitance ($V_{DS} = 10$ V) ($V_{DS} = 6.0$ V) ($V_{DS} = 4.0$ V, f = 1.0 MHz)		C_{iss}	—	18	pF
FUNCTIONAL CHARACTERISTICS					
Noise Figure ($V_{DS} = 10$ V, $R_G = 1.0$ mΩ, f = 1.0 kHz)		NF	—	2.0	dB

*Pulse Width ≤ 630 ms, Duty Cycle ≤ 10%.

6

2N3459
2N3460

CASE 22-03, STYLE 4
TO-18 (TO-206AA)



JFET
LOW-FREQUENCY/
LOW NOISE

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V_{DG}	50	Vdc
Gate-Source Voltage	V_{GS}	50	Vdc
Gate Current	I_G	10	mA
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 1.7	mW mW/°C
Storage Temperature Range	T_{stg}	−65 to +200	°C

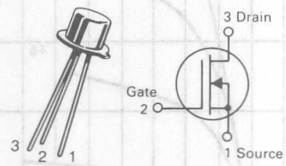
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = 1.0 μA)		$V_{(BR)GSS}$	−50	—	Vdc
Gate Reverse Current (V_{GS} = −30 V)		I_{GSS}	—	−0.25	nA
Gate Source Cutoff Voltage (V_{DS} = 20 V, I_D = 1.0 μA)	2N3459 2N3460	$V_{GS(off)}$	— —	−3.4 −1.8	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current (V_{DS} = 20 Volts)	2N3459 2N3460	I_{DSS}*	0.8 0.2	4.0 1.0	mA
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance (V_{DS} = 20 Volts, f = 1.0 kHz)	2N3459 2N3460	$\|y_{fs}\|$*	1500 800	6000 4500	μmhos
Output Admittance (V_{DS} = 30 Volts, f = 1.0 kHz)	2N3459 2N3460	$\|y_{os}\|$	— —	20 5.0	μmhos
Input Capacitance (V_{DS} = 10 V)		C_{iss}	—	18	pF
Output Capacitance (V_{DS} = 30 V)		C_{oss}	—	5.0	pF
FUNCTIONAL CHARACTERISTICS					
Noise Figure (V_{DS} = 10 V, f = 20 Hz, R_G = 1.0 MΩ)	2N3459 2N3460	NF	— —	4.0 4.0	dB

*Pulse Width ≤ 100 ms, Duty Cycle ≤ 10%.

2N3796
2N3797

CASE 22-03, STYLE 2
TO-18 (TO-206AA)



MOSFET
LOW-POWER AUDIO

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage 2N3796 / 2N3797	V_{DS}	25 / 20	Vdc
Gate-Source Voltage	V_{GS}	± 10	Vdc
Drain Current	I_D	20	mAdc
Total Device Dissipation @ $T_A = 25°C$ / Derate above 25°C	P_D	200 / 1.14	mW / mW/°C
Junction Temperature Range	T_J	+175	°C
Storage Channel Temperature Range	T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage		$V_{(BR)DSX}$				Vdc
($V_{GS} = -4.0$ V, $I_D = 5.0\ \mu A$)	2N3796		25	30	—	
($V_{GS} = -7.0$ V, $I_D = 5.0\ \mu A$)	2N3797		20	25	—	
Gate Reverse Current(1)		I_{GSS}				pAdc
($V_{GS} = -10$ V, $V_{DS} = 0$)			—	—	1.0	
($V_{GS} = -10$ V, $V_{DS} = 0$, $T_A = 150°C$)			—	—	200	
Gate Source Cutoff Voltage		$V_{GS(off)}$				Vdc
($I_D = 0.5\ \mu A$, $V_{DS} = 10$ V)	2N3796		—	−3.0	−4.0	
($I_D = 2.0\ \mu A$, $V_{DS} = 10$ V)	2N3797		—	−5.0	−7.0	
Drain-Gate Reverse Current(1) ($V_{DG} = 10$ V, $I_S = 0$)		I_{DGO}	—	—	1.0	pAdc
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current		I_{DSS}				mAdc
($V_{DS} = 10$ V, $V_{GS} = 0$)	2N3796		0.5	1.5	3.0	
	2N3797		2.0	2.9	6.0	
On-State Drain Current		$I_{D(on)}$				mAdc
($V_{DS} = 10$ V, $V_{GS} = +3.5$ V)	2N3796		7.0	8.3	14	
	2N3797		9.0	14	18	
SMALL-SIGNAL CHARACTERISTICS						
Forward Transfer Admittance		$\lvert y_{fs} \rvert$				µmhos
($V_{DS} = 10$ V, $V_{GS} = 0$, f = 1.0 kHz)	2N3796		900	1200	1800	
	2N3797		1500	2300	3000	
($V_{DS} = 10$ V, $V_{GS} = 0$, f = 1.0 MHz)	2N3796		900	—	—	
	2N3797		1500	—	—	
Output Admittance		$\lvert y_{os} \rvert$				µmhos
($V_{DS} = 10$ V, $V_{GS} = 0$, f = 1.0 kHz)	2N3796		—	12	25	
	2N3797		—	27	60	
Input Capacitance		C_{iss}				pF
($V_{DS} = 10$ V, $V_{GS} = 0$, f = 1.0 MHz)	2N3796		—	5.0	7.0	
	2N3797		—	6.0	8.0	
Reverse Transfer Capacitance ($V_{DS} = 10$ V, $V_{GS} = 0$, f = 1.0 MHz)		C_{rss}	—	0.5	0.8	pF
FUNCTIONAL CHARACTERISTICS						
Noise Figure ($V_{DS} = 10$ V, $V_{GS} = 0$, f = 1.0 kHz, $R_S = 3$ megohms)		NF	—	3.8	—	dB

(1) This value of current includes both the FET leakage current as well as the leakage current associated with the test socket and fixture when measured under best attainable conditions.

6

TYPICAL DRAIN CHARACTERISTICS

FIGURE 1 — 2N3796

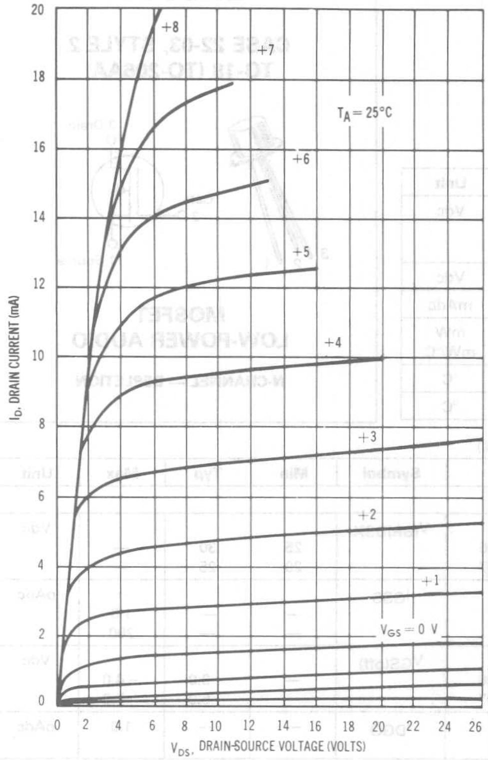
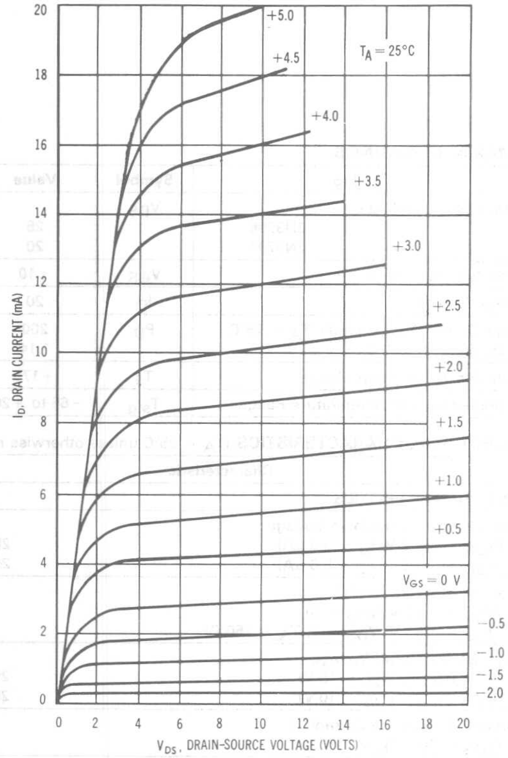


FIGURE 2 — 2N3797



COMMON SOURCE TRANSFER CHARACTERISTICS

FIGURE 3 — 2N3796

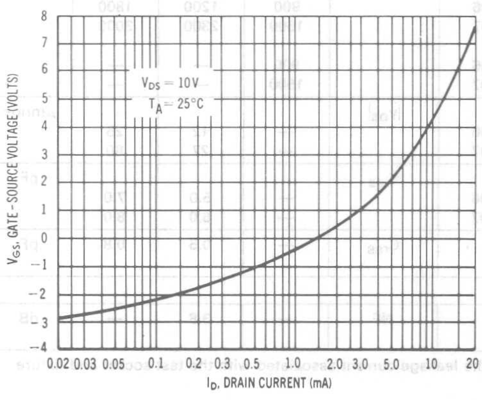


FIGURE 4 — 2N3797

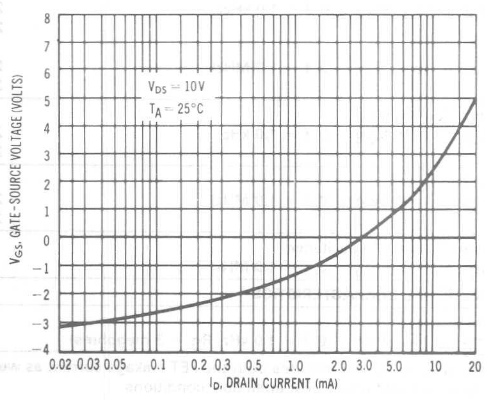


FIGURE 5 — FORWARD TRANSFER ADMITTANCE

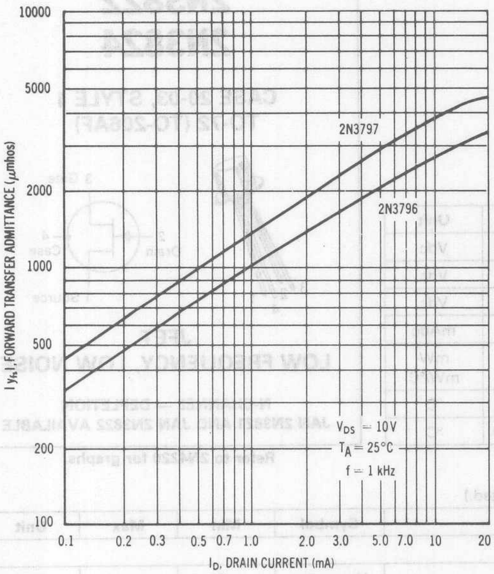


FIGURE 6 — OUTPUT ADMITTANCE

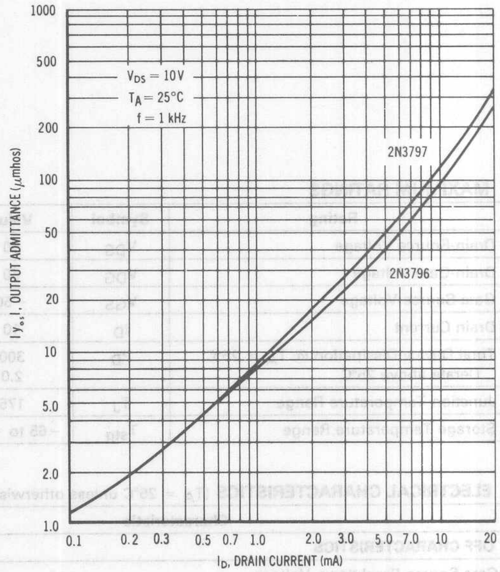
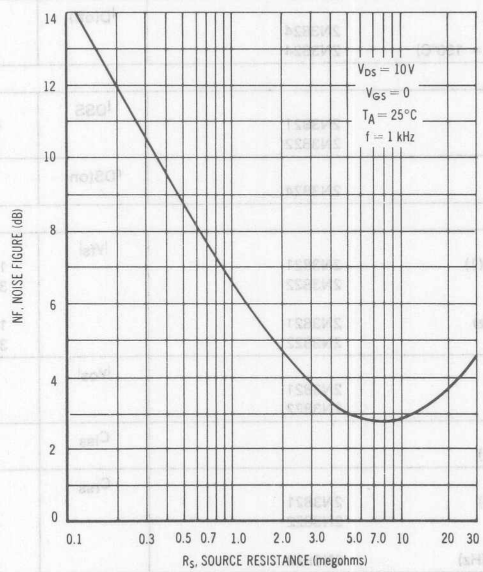


FIGURE 7 — NOISE FIGURE

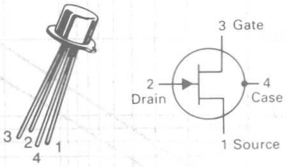


6

6

2N3821
2N3822
2N3824

CASE 20-03, STYLE 1
TO-72 (TO-206AF)



JFET
LOW FREQUENCY, LOW NOISE

N-CHANNEL — DEPLETION
JAN 2N3821 AND JAN 2N3822 AVAILABLE

Refer to 2N4220 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	50	Vdc
Drain-Gate Voltage	V_{DG}	50	Vdc
Gate-Source Voltage	V_{GS}	−50	Vdc
Drain Current	I_D	10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 2.0	mW mW/°C
Junction Temperature Range	T_J	175	°C
Storage Temperature Range	T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = −1.0 μAdc, V_{DS} = 0)		$V_{(BR)GSS}$	−50	—	Vdc
Gate Reverse Current (V_{GS} = −30 Vdc, V_{DS} = 0) (V_{GS} = −30 Vdc, V_{DS} = 0, T_A = 150°C)		I_{GSS}	 — —	 −0.1 −100	nAdc
Gate Source Cutoff Voltage (I_D = 0.5 nAdc, V_{DS} = 15 Vdc)	 2N3821 2N3822	$V_{GS(off)}$	 — —	 −4.0 −6.0	Vdc
Gate Source Voltage (I_D = 50 μAdc, V_{DS} = 15 Vdc) (I_D = 200 μAdc, V_{DS} = 15 Vdc)	 2N3821 2N3822	V_{GS}	 −0.5 −1.0	 −2.0 −4.0	Vdc
Drain Cutoff Current (V_{DS} = 15 Vdc, V_{GS} = −8.0 Vdc) (V_{DS} = 15 Vdc, V_{GS} = −8.0 Vdc, T_A = 150°C)	 2N3824 2N3824	$I_{D(off)}$	 — —	 0.1 100	nAdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current(1) (V_{DS} = 15 Vdc, V_{GS} = 0)	 2N3821 2N3822	I_{DSS}	 0.5 2.0	 2.5 10	mAdc
Static Drain-Source On Resistance (V_{GS} = 0, I_D = 0, f = 1.0 kHz)	 2N3824	$r_{DS(on)}$	—	250	Ohms
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)(1) (V_{DS} = 15 Vdc, V_{GS} = 0, f = 100 MHz)	 2N3821 2N3822 2N3821 2N3822	$\|y_{fs}\|$	 1500 3000 1500 3000	 4500 6500 — —	μmhos
Output Admittance(1) (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)	 2N3821 2N3822	$\|y_{os}\|$	 — —	 10 20	μmhos
Input Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	6.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz) (V_{GS} = −8.0 Vdc, V_{DS} = 0, f = 1.0 MHz)	 2N3821 2N3822 2N3824	C_{rss}	 — — —	 3.0 3.0 3.0	pF

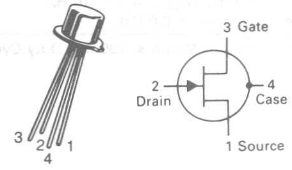
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
FUNCTIONAL CHARACTERISTICS					
Noise Figure (V_{DS} = 15 Vdc, V_{GS} = 0, R_S = 1.0 megohm, f = 10 Hz, Noise Bandwidth = 5.0 Hz)	2N3821, 2N3822	NF	—	5.0	dB
Equivalent Input Noise Voltage (V_{DS} = 15 Vdc, V_{GS} = 0, f = 10 Hz, Noise Bandwidth = 5.0 Hz)	2N3821, 2N3822	e_n	—	200	nv/Hz$^{1/2}$

(1) Pulse Test: Pulse Width ≤ 100 ms, Duty Cycle ≤ 10%.

2N3823

JAN, JANTX AVAILABLE
CASE 20-03, STYLE 1
TO-72 (TO-206AF)



JFET
VHF AMPLIFIER

N-CHANNEL — DEPLETION

Refer to 2N4416 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage	V_{GS}	−30	Vdc
Gate Current	I_G	10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 2.0	mW mW/°C
Junction Temperature Range	T_J	175	°C
Storage Temperature Range	T_{stg}	−65 to +200	°C

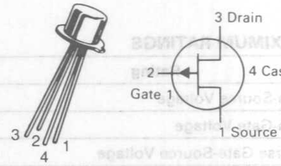
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage (I_G = −1.0 μAdc, V_{DS} = 0)	$V_{(BR)GSS}$	−30	—	Vdc
Gate Reverse Current (V_{GS} = −20 Vdc, V_{DS} = 0) (V_{GS} = −20 Vdc, V_{DS} = 0, T_A = 150°C)	I_{GSS}	 — —	 −0.5 −500	nAdc
Gate Source Cutoff Voltage (I_D = 0.5 nAdc, V_{DS} = 15 Vdc)	$V_{GS(off)}$	—	−8.0	Vdc
Gate Source Voltage (I_D = 0.4 mAdc, V_{DS} = 15 Vdc)	V_{GS}	−1.0	−7.5	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current(1) (V_{DS} = 15 Vdc, V_{GS} = 0)	I_{DSS}	4.0	20	mAdc
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)(1) (V_{DS} = 15 Vdc, V_{GS} = 0, f = 200 MHz)	$\|y_{fs}\|$	 3500 3200	 6500 —	μmhos
Input Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 200 MHz)	$Re(y_{is})$	—	800	μmhos
Output Conductance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)(1) (V_{DS} = 15 Vdc, V_{GS} = 0, f = 200 MHz)	 $\|y_{os}\|$ $Re(y_{os})$	 — —	 35 200	μmhos
Input Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	6.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{rss}	—	2.0	pF
FUNCTIONAL CHARACTERISTICS				
Noise Figure (V_{DS} = 15 Vdc, V_{GS} = 0, R_S = 1000 ohms, f = 100 MHz)	NF	—	2.5	dB

(1) Pulse Test: Pulse Width = 100 ms, Duty Cycle ≤ 10%.

2N3909
2N3909A

CASE 20-03, STYLE 5
TO-72 (TO-206AF)



JFET
AMPLIFIER

P-CHANNEL — DEPLETION

Refer to 2N5460 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	−20	Vdc
Drain-Gate Voltage	V_{DG}	−20	Vdc
Reverse Gate-Source Voltage	V_{GSR}	20	Vdc
Forward Gate Current	I_{GF}	10	mAdc
Forward Gate-Source Voltage	V_{GSF}	20	Vdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	300 2.0	mW mW/°C
Storage Temperature Range	T_{stg}	−65 to +200	°C

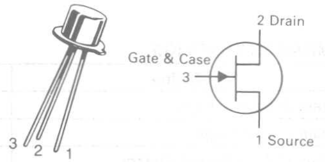
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.) (1)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = 10\ \mu Adc$, $V_{DS} = 0$)		$V_{(BR)GSS}$	20	—	Vdc
Gate Reverse Current ($V_{GS} = 10$ Vdc, $V_{DS} = 0$) ($V_{GS} = 10$ Vdc, $V_{DS} = 0$, $T_A = 100°C$)		I_{GSS}	 — —	 10 1.0	 nAdc μAdc
Gate Source Cutoff Voltage ($V_{DS} = -10$ Vdc, $I_D = 10\ \mu Adc$)	 2N3909 2N3909A	$V_{GS(off)}$	 — —	 8.0 8.0	Vdc
Gate Source Voltage ($V_{DS} = -10$ Vdc, $I_D = 30\ \mu Adc$)		V_{GS}	0.3	7.9	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current(2) ($V_{DS} = -10$ Vdc, $V_{GS} = 0$)	 2N3909 2N3909A	I_{DSS}	 0.3 1.0	 15 15	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance(2) ($V_{DS} = -10$ Vdc, $V_{GS} = 0$, f = 1.0 kHz)	 2N3909 2N3909A	$\lvert y_{fs} \rvert$	 1000 2200	 5000 5000	μmhos
($V_{DS} = -10$ Vdc, $V_{GS} = 0$, f = 10 MHz)	2N3909 2N3909A		900 2000	— —	
Output Admittance ($V_{DS} = -10$ Vdc, $V_{GS} = 0$, f = 1.0 kHz)		$\lvert y_{os} \rvert$	—	100	μmhos
Input Capacitance ($V_{DS} = -10$ Vdc, $V_{GS} = 0$, f = 1.0 MHz)	 2N3909 2N3909A	C_{iss}	 — —	 32 9.0	pF
Reverse Transfer Capacitance ($V_{DS} = -10$ Vdc, $V_{GS} = 0$, f = 1.0 MHz)	 2N3909 2N3909A	C_{rss}	 — —	 16 3.0	pF

(1) The fourth lead (case) is connected to the source for all measurements.
(2) Pulse Test: Pulse Width ≤ 630 ms, Duty Cycle ≤ 10%.

2N3970
2N3971
2N3972

CASE 22-03, STYLE 4
TO-18 (TO-206AA)



JFET
SWITCHING

N-CHANNEL — DEPLETION

6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	40	Vdc
Drain-Gate Voltage	V_{DG}	40	Vdc
Reverse Gate-Source Voltage	V_{GSR}	40	Vdc
Forward Gate Current	I_{GF}	50	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.8 10	Watts mW/°C
Storage Temperature Range	T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = 1.0\ \mu Adc$, $V_{GS} = 0$)		$V_{(BR)GSS}$	40	—	Vdc
Gate Reverse Current ($V_{GS} = 20$ Vdc, $V_{DS} = 0$)		I_{GSS}	—	250	pAdc
Drain Reverse Current ($V_{DG} = 20$ Vdc, $I_S = 0$) ($V_{DG} = 20$ Vdc, $I_S = 0$, $T_A = 150°C$)		I_{DGO}	— —	250 500	pAdc nAdc
Drain Cutoff Current ($V_{DS} = 20$ Vdc, $V_{GS} = -12$ Vdc) ($V_{DS} = 20$ Vdc, $V_{GS} = -12$ Vdc, $T_A = 150°C$)		$I_{D(off)}$	— —	250 500	pAdc nAdc
Gate Source Voltage ($V_{DS} = 20$ Vdc, $I_D = 1.0$ nAdc)	2N3970 2N3971 2N3972	V_{GS}	4.0 2.0 0.5	10 5.0 3.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current(1) ($V_{DS} = 20$ Vdc, $V_{GS} = 0$)	2N3970 2N3971 2N3972	I_{DSS}	50 25 5.0	150 75 30	mAdc
Drain-Source On-Voltage ($I_D = 20$ mAdc, $V_{GS} = 0$) ($I_D = 10$ mAdc, $V_{GS} = 0$) ($I_D = 5.0$ mAdc, $V_{GS} = 0$)	2N3970 2N3971 2N3972	$V_{DS(on)}$	— — —	1.0 1.5 2.0	Vdc
Static Drain-Source On Resistance ($I_D = 1.0$ mAdc, $V_{GS} = 0$)	2N3970 2N3971 2N3972	$r_{DS(on)}$	— — —	30 60 100	Ohms
SMALL-SIGNAL CHARACTERISTICS					
Drain-Source "ON" Resistance ($V_{GS} = 0$, $I_D = 0$, f = 1.0 kHz)	2N3970 2N3971 2N3972	$r_{ds(on)}$	— — —	30 60 100	Ohms
Input Capacitance ($V_{DS} = 20$ Vdc, $V_{GS} = 0$, f = 1.0 MHz)		C_{iss}	—	25	pF
Reverse Transfer Capacitance ($V_{DS} = 0$, $V_{GS} = -12$ Vdc, f = 1.0 MHz)		C_{rss}	—	6.0	pF

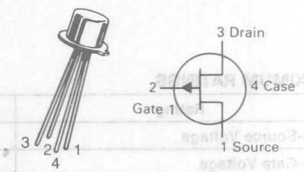
SWITCHING CHARACTERISTICS

Characteristic	Test Condition	Device	Symbol	Min	Max	Unit
Turn-On Delay Time	Test Condition for 2N3970: ($V_{DD} = 10$ Vdc, $V_{GS(on)} = 0$, $I_{D(on)} = 20$ mAdc, $V_{GS(off)} = 10$ Vdc)	2N3970 2N3971 2N3972	$t_{d(on)}$	— — —	10 15 40	ns
Rise Time	Test Condition for 2N3971: ($V_{DD} = 10$ Vdc, $V_{GS(on)} = 0$, $I_{D(on)} = 10$ mAdc, $V_{GS(on)} = 5.0$ Vdc)	2N3970 2N3971 2N3972	t_r	— — —	10 15 40	ns
Turn-Off Time	Test Condition for 2N3972: ($V_{DD} = 10$ Vdc, $V_{GS(on)} = 0$, $I_{D(on)} = 5.0$ mAdc, $V_{GS(off)} = 3.0$ Vdc)	2N3970 2N3971 2N3972	t_{off}	— — —	30 60 100	ns

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 3.0%.

2N3993,A
2N3994

CASE 20-03, STYLE 5
TO-72 (TO-206AF)



JFET SWITCHING

P-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	−25	Vdc
Drain-Gate Voltage	V_{DG}	−25	Vdc
Reverse Gate-Source Voltage	V_{GSR}	25	Vdc
Forward Gate Current	I_{GF}	10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 2.0	mW mW/°C
Storage Temperature Range	T_{stg}	−65 to +200	°C

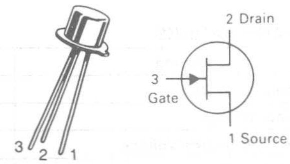
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = 1.0 μAdc, V_{DS} = 0)		$V_{(BR)GSS}$	25	—	Vdc
Drain Reverse Current (V_{DG} = −15 Vdc, I_S = 0) (V_{DG} = −15 Vdc, I_S = 0, T_A = 150°C)		I_{DGO}	— —	1.2 1.2	nAdc μAdc
Drain Cutoff Current (V_{DS} = −10 Vdc, V_{GS} = 10 Vdc) (V_{DS} = −10 Vdc, V_{GS} = 6.0 Vdc) (V_{DS} = −10 Vdc, V_{GS} = 10 Vdc, T_A = 150°) (V_{DS} = −10 Vdc, V_{GS} = 6.0 Vdc, T_A = 150°)	2N3993, 2N3993A 2N3994 2N3993, 2N3993A 2N3994	$I_{D(off)}$	— — — —	1.2 1.2 1.0 1.0	nAdc μAdc
Gate Source Voltage (V_{DS} = −10 Vdc, I_D = −1.0 μAdc)	2N3993, 2N3993A 2N3994	V_{GS}	4.0 1.0	9.5 5.5	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current(1) (V_{DS} = −10 Vdc, V_{GS} = 0)	2N3993, 2N3993A 2N3994	I_{DSS}	10 2.0	—	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Drain-Source "ON" Resistance (V_{GS} = 0, I_D = 0, f = 1.0 kHz)	2N3993, 2N3993A 2N3994	$r_{ds(on)}$	— —	150 300	Ohms
Forward Transfer Admittance(1) (V_{DS} = −10 Vdc, V_{GS} = 0, f = 1.0 kHz)	2N3993 2N3993A 2N3994	$\lvert y_{fs} \rvert$	6.0 7.0 4.0	12 12 10	mmhos
Input Capacitance (V_{DS} = −10 Vdc, V_{GS} = 0, f = 1.0 MHz)	2N3993, 2N3994 2N3993A	C_{iss}	— —	16 12	pF
Reverse Transfer Capacitance (V_{DS} = 0, V_{GS} = 10 Vdc, f = 1.0 MHz)	2N3993 2N3993A	C_{rss}	— —	4.5 3.0	pF
(V_{DS} = 0, V_{GS} = 6.0 Vdc, f = 1.0 MHz)	2N3994		—	5.0	

(1) Pulse Test: Pulse Width = 100 ms, Duty Cycle ≤ 10%.

2N4091
2N4092
2N4093

JAN, JTX AVAILABLE
CASE 22-03, STYLE 3
TO-18 (TO-206AA)



JFET
SWITCHING

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	40	Vdc
Drain-Gate Voltage	V_{DG}	40	Vdc
Gate-Source Voltage	V_{GS}	40	Vdc
Gate Current	I_G	10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.8 10	Watts mW/°C
Junction Temperature Range	T_J	−65 to +175	°C
Storage Temperature Range	T_{stg}	−65 to +175	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

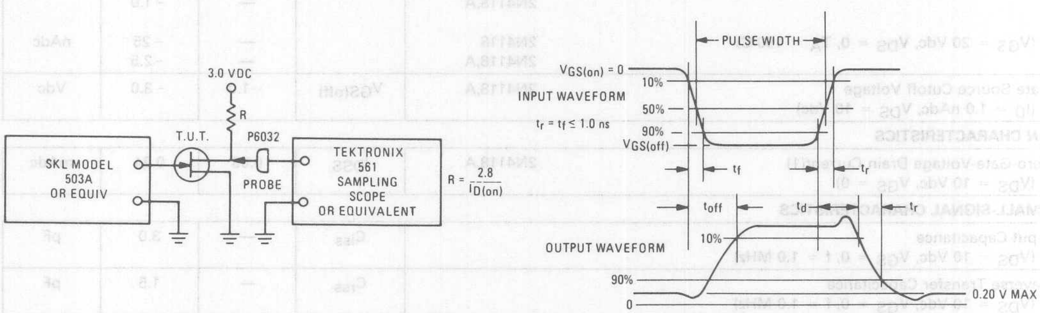
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = 1.0 μAdc, V_{DS} = 0)		$V_{(BR)GSS}$	40	—	Vdc
Drain-Gate Breakdown Voltage (I_D = 1.0 μAdc, I_S = 0)		$V_{(BR)DGO}$	40	—	Vdc
Gate Source Cutoff Voltage (V_{DS} = 20 Vdc, I_D = 1.0 nAdc)	2N4091 2N4092 2N4093	$V_{GS(off)}$	5.0 2.0 1.0	10 7.0 5.0	Vdc
Source Reverse Current (V_{SG} = 20 Vdc, I_D = 0)		I_{SGO}	—	0.2	nAdc
Drain Reverse Current (V_{DG} = 20 Vdc, I_S = 0) (V_{DG} = 20 Vdc, I_D = 0, T_A = 150°C)		I_{DGO}	— —	0.2 0.4	nAdc μAdc
Drain-Cutoff Current (V_{DS} = 20 Vdc, V_{GS} = 12 Vdc) (V_{DS} = 20 Vdc, V_{GS} = 8.0 Vdc) (V_{DS} = 20 Vdc, V_{GS} = 6.0 Vdc) (V_{DS} = 20 Vdc, V_{GS} = 12 Vdc, T_A = 150°C) (V_{DS} = 20 Vdc, V_{GS} = 8.0 Vdc, T_A = 150°C) (V_{DS} = 20 Vdc, V_{GS} = 6.0 Vdc, T_A = 150°C)	2N4091 2N4092 2N4093 2N4091 2N4092 2N4093	$I_{D(off)}$	— — — — — —	0.2 0.2 0.2 0.4 0.4 0.4	nAdc μAdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current* (V_{DS} = 20 Vdc, V_{GS} = 0)	2N4091 2N4092 2N4093	I_{DSS}*	30 15 8.0	— — —	mAdc
Drain-Source On-Voltage (I_D = 6.6 mAdc, V_{GS} = 0) (I_D = 4.0 mAdc, V_{GS} = 0) (I_D = 2.5 mAdc, V_{GS} = 0)	2N4091 2N4092 2N4093	$V_{DS(on)}$	— — —	0.2 0.2 0.2	Vdc
Static Drain-Source On Resistance (I_D = 1.0 mAdc, V_{GS} = 0)	2N4091 2N4092 2N4093	$r_{DS(on)}$	— — —	30 50 80	Ohms

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Drain-Source "ON" Resistance (V_{GS} = 0, I_D = 0, f = 1.0 kHz)	2N4091	$r_{ds(on)}$	—	30	Ohms
	2N4092		—	50	
	2N4093		—	80	
Input Capacitance (V_{DS} = 20 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	16	pF
Reverse Transfer Capacitance (V_{DS} = 0, V_{GS} = 20 Vdc, f = 1.0 MHz)		C_{rss}	—	5.0	pF
SWITCHING CHARACTERISTICS					
Delay Time (See Figure 1)		t_d			ns
($I_{D(on)}$ = 6.6 mAdc)	2N4091		—	15	
($I_{D(on)}$ = 4.0 mAdc)	2N4092		—	15	
($I_{D(on)}$ = 2.5 mAdc)	2N4093		—	20	
Rise Time (See Figure 1)		t_r			ns
($I_{D(on)}$ = 6.6 mAdc)	2N4091		—	10	
($I_{D(on)}$ = 4.0 mAdc)	2N4092		—	20	
($I_{D(on)}$ = 2.5 mAdc)	2N4093		—	40	
Turn-Off Time (See Figure 1)		t_{off}			ns
($V_{GS(off)}$ = 12 Vdc)	2N4091		—	40	
($V_{GS(off)}$ = 8.0 Vdc)	2N4092		—	60	
($V_{GS(off)}$ = 6.0 Vdc)	2N4093		—	80	

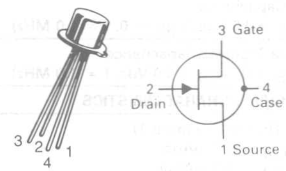
*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 3.0%.

FIGURE 1 – SWITCHING TIMES TEST CIRCUIT



2N4118,A

CASE 20-03, STYLE 1
TO-72 (TO-206AF)



JFET
AMPLIFIER

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	−40	Vdc
Drain-Gate Voltage	V_{DG}	−40	Vdc
Gate Current	I_G	50	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 2.0	mW mW/°C
Lead Temperature (1/16″ from case for 10 s)	T_L	255	°C
Storage Temperature Range	T_{stg}	−65 to +175	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = −1.0 μAdc, V_{DS} = 0)		$V_{(BR)GSS}$	−40	—	Vdc
Gate Reverse Current (V_{GS} = 20 Vdc, V_{DS} = 0)	2N4118 2N4118,A	I_{GSS}	— —	−10 −1.0	pAdc
(V_{GS} = 20 Vdc, V_{DS} = 0, T_A = 150°C)	2N4118 2N4118,A		— —	−25 −2.5	nAdc
Gate Source Cutoff Voltage (I_D = 1.0 nAdc, V_{DS} = 10 Vdc)	2N4118,A	$V_{GS(off)}$	−1.0	−3.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current(1) (V_{DS} = 10 Vdc, V_{GS} = 0)	2N4118,A	I_{DSS}	0.08	0.24	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Input Capacitance (V_{DS} = 10 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	3.0	pF
Reverse Transfer Capacitance (V_{DS} = 10 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	—	1.5	pF
Forward Transconductance (V_{DS} = 10 Vdc, V_{GS} = 0, f = 1.0 kHz)	2N4118,A	g_{fs}	80	250	μmhos
Output Conductance (V_{DS} = 10 Vdc, V_{GS} = 0, f = 1.0 kHz)	2N4118,A	g_{os}	—	5.0	μmhos

(1) I_{DSS} is measured during a 2.0 ms interval 100 ms after power is applied. (NOT a JEDEC condition.)

FIGURE 1 – TRANSFER CHARACTERISTICS

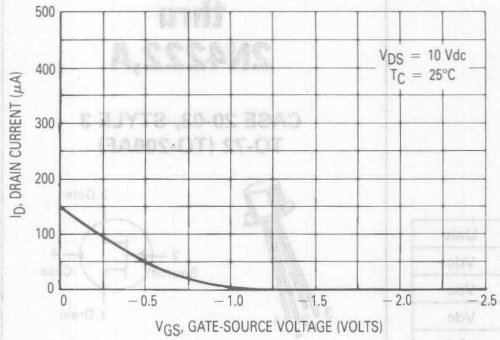
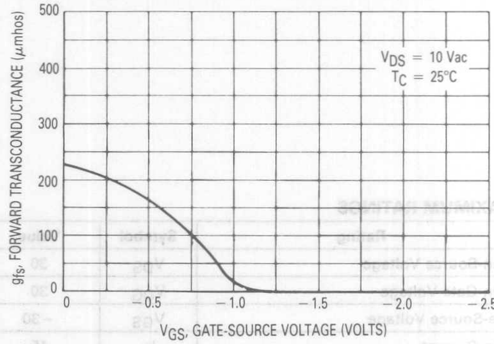


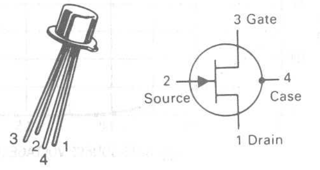
FIGURE 2 – TRANSCONDUCTANCE CHARACTERISTICS



6

2N4220,A
thru
2N4222,A

CASE 20-03, STYLE 3
TO-72 (TO-206AF)



JFET
LOW-FREQUENCY, LOW NOISE

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage	V_{GS}	−30	Vdc
Drain Current	I_D	15	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 2	mW mW/°C
Junction Temperature Range	T_J	175	°C
Storage Channel Temperature Range	T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Gate-Source Breakdown Voltage (I_G = −10 μAdc, V_{DS} = 0)		$V_{(BR)GSS}$	−30	—	—	Vdc
Gate Reverse Current (V_{GS} = −15 Vdc, V_{DS} = 0) (V_{GS} = −15 Vdc, V_{DS} = 0, T_A = 150°C)		I_{GSS}	 — —	 — —	 −0.1 −100	nAdc
Gate Source Cutoff Voltage (I_D = 0.1 nAdc, V_{DS} = 15 Vdc)	2N4220,A 2N4221,A 2N4222,A	$V_{GS(off)}$	— — —	— — —	−4 −6 −8	Vdc
Gate Source Voltage (I_D = 50 μAdc, V_{DS} = 15 Vdc) (I_D = 200 μAdc, V_{DS} = 15 Vdc) (I_D = 500 μAdc, V_{DS} = 15 Vdc)	 2N4220,A 2N4221,A 2N4222,A	V_{GS}	 −0.5 −1.0 −2.0	 — — —	 −2.5 −5.0 −6.0	Vdc
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current* (V_{DS} = 15 Vdc, V_{GS} = 0)	2N4220,A 2N4221,A 2N4222,A	I_{DSS}	0.5 2.0 5.0	— — —	3.0 6.0 15	mAdc
Static Drain-Source On Resistance (V_{DS} = 0, V_{GS} = 0)	2N4220,A 2N4221,A 2N4222,A	$r_{DS(on)}$	— — —	500 400 300	— — —	Ohms
SMALL-SIGNAL CHARACTERISTICS						
Forward Transfer Admittance Common Source* (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)	2N4220,A 2N4221,A 2N4222,A	$\|y_{fs}\|$	1000 2000 2500	— — —	4000 5000 6000	μmhos
Output Admittance Common Source (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)	2N4220,A 2N4221,A 2N4222,A	$\|y_{os}\|$	— — —	— — —	10 20 40	μmhos
Input Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	4.5	6.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	—	1.2	2.0	pF
Common-Source Output Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 30 MHz)		C_{osp}	—	1.5	—	pF

*Pulse Test: Pulse Width = 630 ms, Duty Cycle = 10%.

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
FUNCTIONAL CHARACTERISTICS						
Noise Figure (V_{DS} = 15 Vdc, V_{GS} = 0, R_S = 1.0 megohm, f = 100 Hz)	2N4220A 2N4221A 2N4222A	NF	— — —	— — —	2.5 2.5 2.5	dB

FIGURE 1 — NOISE FIGURE versus FREQUENCY

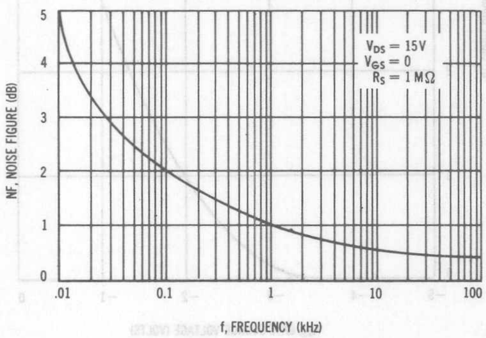


FIGURE 2 — NOISE FIGURE versus SOURCE RESISTANCE

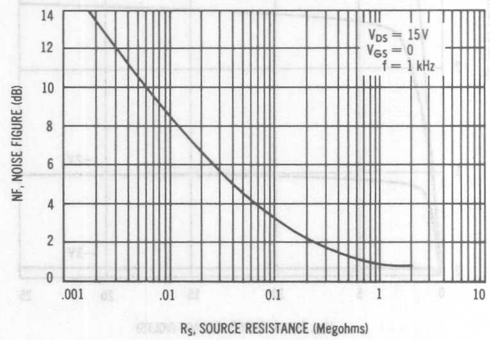


FIGURE 3 — TYPICAL DRAIN CHARACTERISTICS
$V_{GS(off)} \cong -1.2$ VOLTS

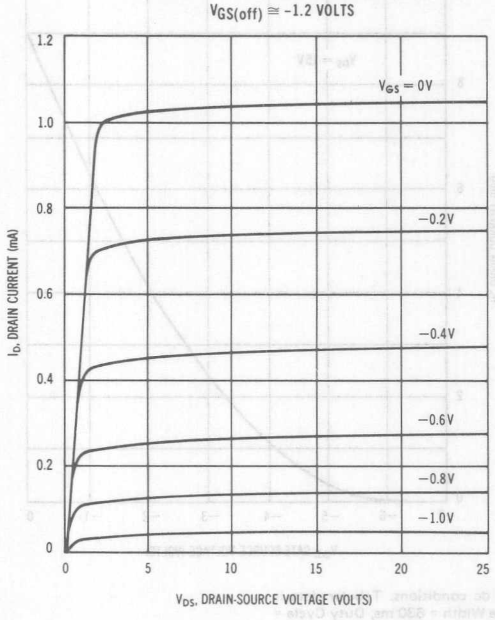
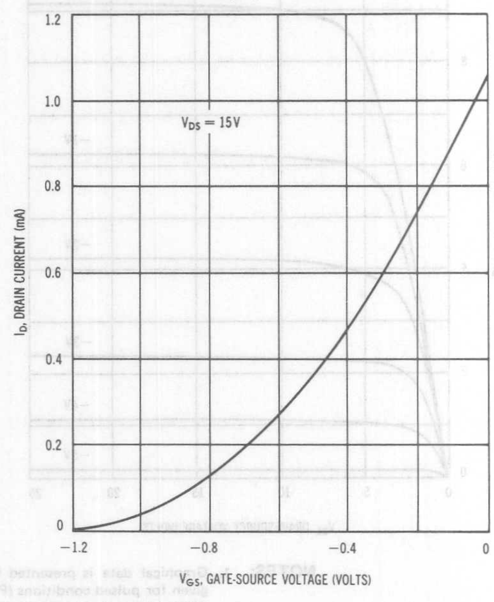


FIGURE 4 — COMMON SOURCE TRANSFER CHARACTERISTICS
$V_{GS(off)} \cong -1.2$ VOLTS



6

FIGURE 5 — TYPICAL DRAIN CHARACTERISTICS
$V_{GS(off)} \cong -3.5$ VOLTS

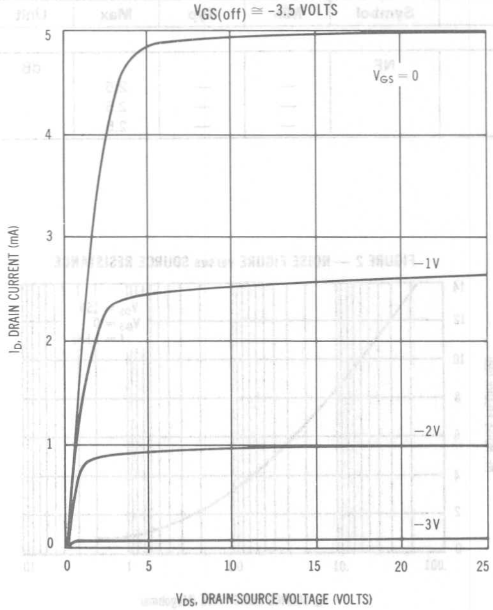


FIGURE 6 — COMMON SOURCE TRANSFER CHARACTERISTICS
$V_{GS(off)} \cong -3.5$ VOLTS

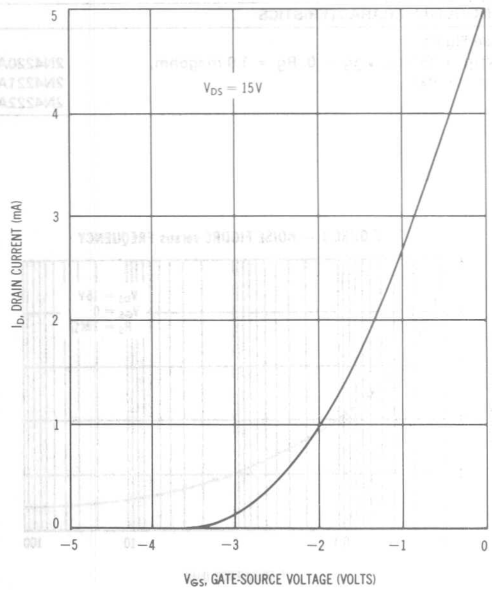


FIGURE 7 — TYPICAL DRAIN CHARACTERISTICS
$V_{GS(off)} \cong -5.8$ VOLTS

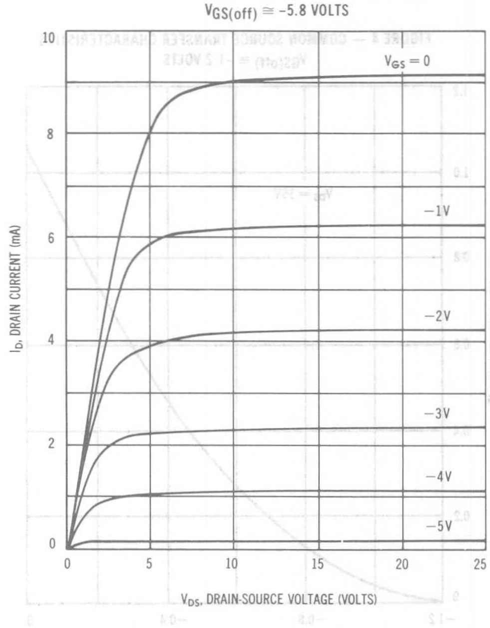
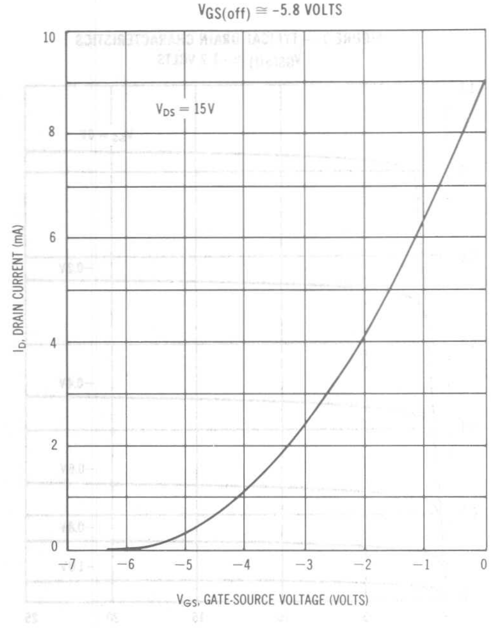


FIGURE 8 — COMMON SOURCE TRANSFER CHARACTERISTICS
$V_{GS(off)} \cong -5.8$ VOLTS

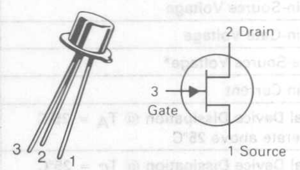


NOTES:

1. Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%). Under dc conditions, self heating in higher I_{DSS} units reduces I_{DSS} (See Figure 10).
2. Figures 8, 9, 10: Data taken in a standard printed circuit with a TO-18 type socket mounting and 1/4" lead length.

2N4338
2N4339
2N4340
2N4341

CASE 22-03, STYLE 3
TO-18 (TO-206AA)



JFET
LOW-FREQUENCY, LOW NOISE

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	50	Vdc
Drain-Gate Voltage	V_{DG}	50	Vdc
Gate-Source Voltage	V_{GS}	50	Vdc
Reverse Gate-Source Voltage	V_{GSR}	50	Vdc
Gate Current	I_G	50	mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	300 2.0	mW mW/°C
Storage Temperature Range	T_{stg}	−65 to +200	°C

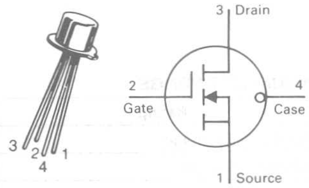
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = -1.0\ \mu A$)		$V_{(BR)GSS}$	50	—	Vdc
Gate Reverse Current ($V_{GS} = -30$ V)		I_{GSS}	—	0.1	nA
Gate Source Cutoff Voltage (V_{DS} = 15 V, $I_D = 0.1\ \mu A$)	2N4338 2N4339 2N4340 2N4341	$V_{GS(off)}$	−0.3 −0.6 −1.0 −2.0	−1.0 −1.8 −3.0 −6.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current (V_{DS} = 15 V)	2N4338 2N4339 2N4340 2N4341	I_{DSS}*	0.2 0.5 1.2 3.0	0.6 1.5 3.6 9.0	mA
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance (V_{DS} = 15 V, f = 1.0 kHz)	2N4338 2N4339 2N4340 2N4341	$\lvert y_{fs} \rvert$*	600 800 1300 2000	1800 2400 3000 4000	μmhos
Output Admittance (V_{DS} = 15 V, f = 1.0 kHz)	2N4338 2N4339 2N4340 2N4341	$\lvert y_{os} \rvert$	— — — —	5.0 15 30 60	μmhos
Input Capacitance (V_{DS} = 15 V, f = 1.0 MHz)		C_{iss}	—	6.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 V, f = 1.0 MHz)		C_{rss}	—	2.0	pF
FUNCTIONAL CHARACTERISTICS					
Noise Figure (V_{DS} = 15 Volts, f = 1.0 kHz, R_G = 1.0 MΩ)		NF	—	1.0	dB

*Pulse Test: Pulse Width ≤ 630 ms, Duty Cycle ≤ 10%.

6

CASE 20-03, STYLE 2
TO-72 (TO-206AF)



MOSFET SWITCHING

N-CHANNEL — ENHANCEMENT

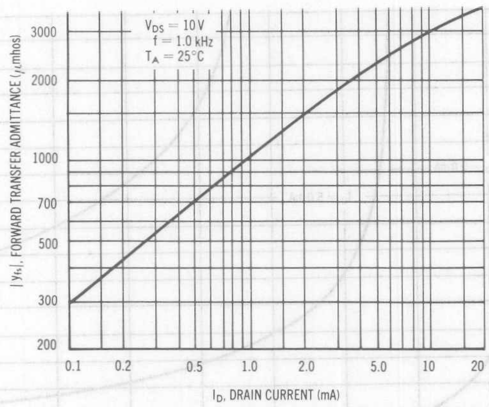
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage*	V_{GS}	30	Vdc
Drain Current	I_D	30	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 1.7	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	800 4.56	mW mW/°C
Junction Temperature Range	T_J	175	°C
Storage Temperature Range	T_{stg}	−65 to +175	°C

*Transient potentials of ±75 Volt will not cause gate-oxide failure.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Drain-Source Breakdown Voltage (I_D = 10 μA, V_{GS} = 0)	$V_{(BR)DSX}$	25	—	Vdc
Zero-Gate-Voltage Drain Current (V_{DS} = 10 V, V_{GS} = 0) T_A = 25°C T_A = 150°C	I_{DSS}	— —	10 10	nAdc μAdc
Gate Reverse Current (V_{GS} = ±15 Vdc, V_{DS} = 0)	I_{GSS}	—	±10	pAdc
ON CHARACTERISTICS				
Gate Threshold Voltage (V_{DS} = 10 V, I_D = 10 μA)	$V_{GS(Th)}$	1.0	5	Vdc
Drain-Source On-Voltage (I_D = 2.0 mA, V_{GS} = 10 V)	$V_{DS(on)}$	—	1.0	V
On-State Drain Current (V_{GS} = 10 V, V_{DS} = 10 V)	$I_{D(on)}$	3.0	—	mAdc
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance (V_{DS} = 10 V, I_D = 2.0 mA, f = 1.0 kHz)	$\lvert y_{fs} \rvert$	1000	—	μmho
Input Capacitance (V_{DS} = 10 V, V_{GS} = 0, f = 140 kHz)	C_{iss}	—	5.0	pF
Reverse Transfer Capacitance (V_{DS} = 0, V_{GS} = 0, f = 140 kHz)	C_{rss}	—	1.3	pF
Drain-Substrate Capacitance ($V_{D(SUB)}$ = 10 V, f = 140 kHz)	$C_{d(sub)}$	—	5.0	pF
Drain-Source Resistance (V_{GS} = 10 V, I_D = 0, f = 1.0 kHz)	$r_{ds(on}$	—	300	ohms
SWITCHING CHARACTERISTICS (I_D = 2.0 mAdc, V_{DS} = 10 Vdc, V_{GS} = 10 Vdc) (See Figure 9; Times Circuit Determined)				
Turn-On Delay (Fig. 5)	t_{d1}	—	45	ns
Rise Time (Fig. 6)	t_r	—	65	ns
Turn-Off Delay (Fig. 7)	t_{d2}	—	60	ns
Fall Time (Fig. 8)	t_f	—	100	ns



6

FIGURE 2 — TRANSFER CHARACTERISTICS

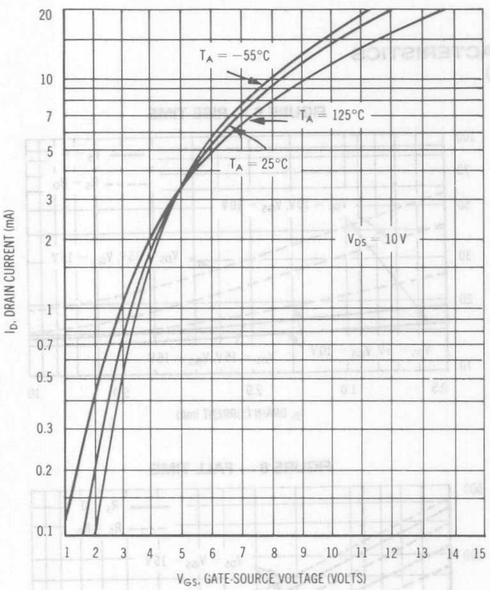


FIGURE 3 — DRAIN-SOURCE "ON" RESISTANCE

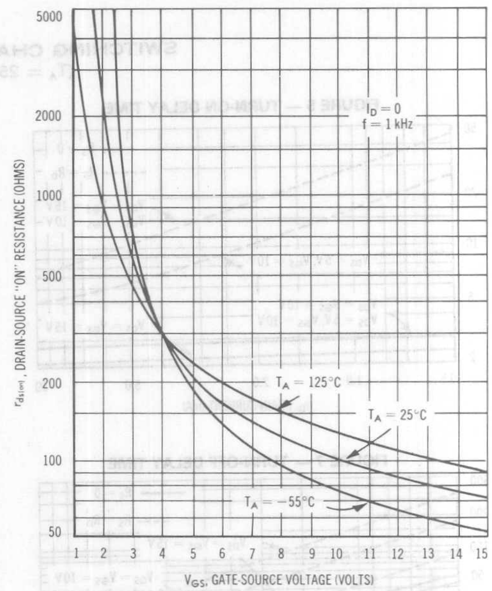
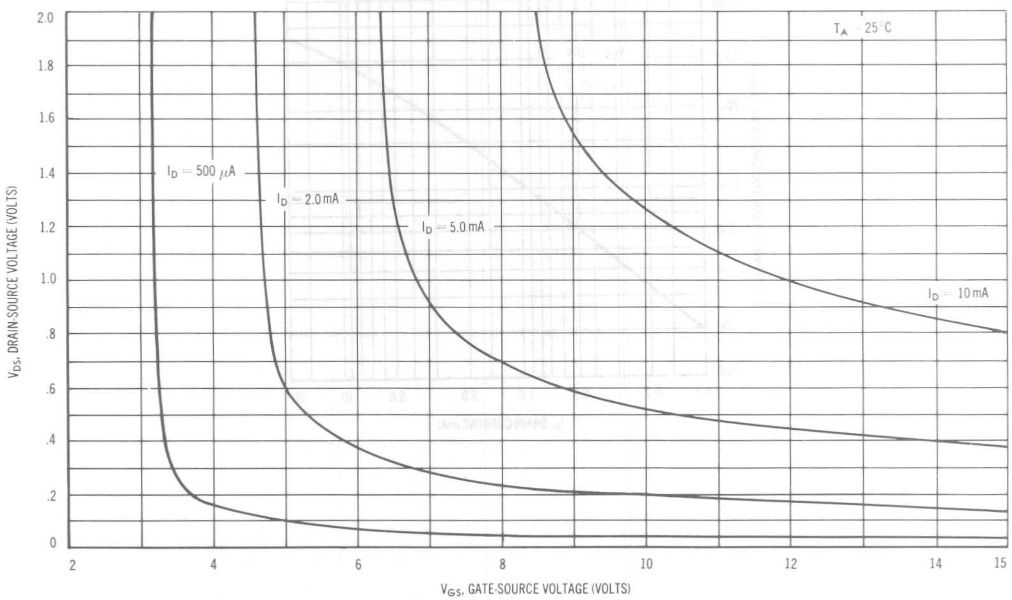


FIGURE 4 — "ON" DRAIN-SOURCE VOLTAGE



6

SWITCHING CHARACTERISTICS

($T_A = 25°C$)

FIGURE 5 — TURN-ON DELAY TIME

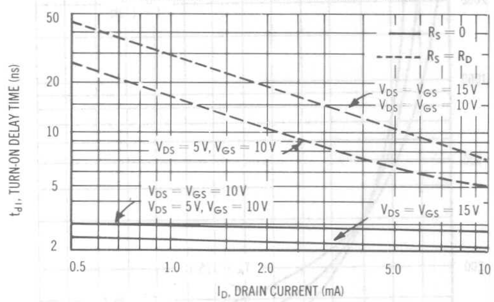


FIGURE 6 — RISE TIME

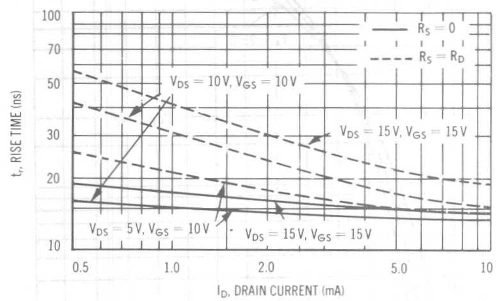


FIGURE 7 — TURN-OFF DELAY TIME

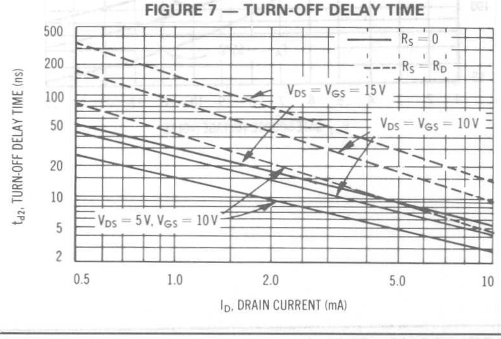


FIGURE 8 — FALL TIME

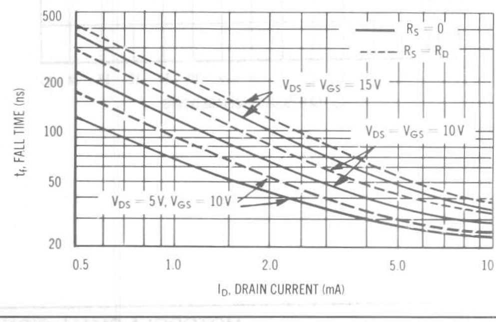
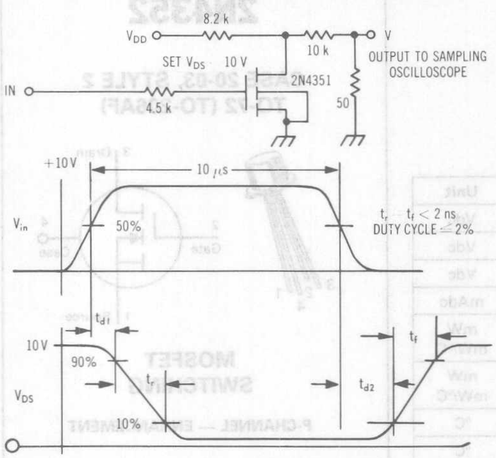


FIGURE 9 — SWITCHING CIRCUIT and WAVEFORMS



The switching characteristics shown above were measured in a test circuit similar to Figure 10. At the beginning of the switching interval, the gate voltage is at ground and the gate-source capacitance ($C_{gs} = C_{iss} - C_{rss}$) has no charge. The drain voltage is at V_{DD}, and thus the feedback capacitance (C_{rss}) is charged to V_{DD}. Similarly, the drain-substrate capacitance ($C_{d(sub)}$) is charged to V_{DD} since the substrate and source are connected to ground.

During the turn-on interval, C_{gs} is charged to V_{GS} (the input voltage) through R_S (generator impedance). C_{rss} must be discharged to $V_{GS} - V_{D(on)}$ through R_S and the parallel combination of the load resistor (R_D) and the channel resistance (r_{ds}). In addition, $C_{d(sub)}$ is discharged to a low value ($V_{D(on)}$) through R_D in parallel with r_{ds}. During turn-off this charge flow is reversed.

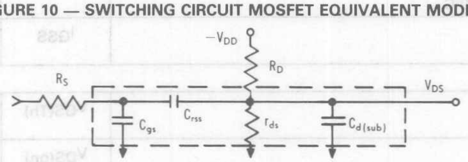
Predicting turn-on time proves to be somewhat difficult since the channel resistance (r_{ds}) is a function of the gate-source voltage (V_{GS}). As C_{gs} becomes charged, V_{GS} is approaching V_{in} and r_{ds} decreases (see Figure 4) and since C_{rss} and $C_{d(sub)}$ are charged through r_{ds}, turn-on time is quite non-linear.

If the charging time of C_{gs} is short compared to that of C_{rss} and $C_{d(sub)}$, then r_{ds} (which is in parallel with R_D) will be low compared to R_D during the switching interval and will largely determine the turn-on time. On the other hand, during turn-off r_{ds} will be almost an open circuit requiring C_{rss} and $C_{d(sub)}$ to be charged through R_D and resulting in a turn-off time that is long compared to the turn-on time. This is especially noticeable for the curves where $R_S = 0$ and C_{gs} is charged through the pulse generator impedance only.

The switching curves shown with $R_S = R_D$ simulate the switching behavior of cascaded stages where the driving source impedance is normally the same as the load impedance. The set of curves with $R_S = 0$ simulates a low source impedance drive such as might occur in complementary logic circuits.

6

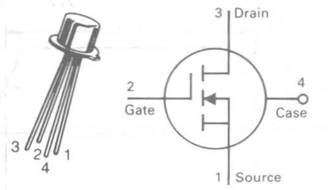
FIGURE 10 — SWITCHING CIRCUIT MOSFET EQUIVALENT MODEL



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage	V_{GS}	±30	Vdc
Drain Current	I_D	30	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	300 1.7	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	800 4.56	mW mW/°C
Junction Temperature Range	T_J	175	°C
Storage Temperature Range	T_{stg}	−65 to +175	°C

CASE 20-03, STYLE 2
TO-72 (TO-206AF)



MOSFET SWITCHING

P-CHANNEL — ENHANCEMENT

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Drain-Source Breakdown Voltage ($I_D = -10\ \mu A$, $V_{GS} = 0$)	$V_{(BR)DSX}$	−25	—	Vdc
Zero-Gate-Voltage Drain Current ($V_{DS} = -10$ V, $V_{GS} = 0$) $T_A = 25°C$ $T_A = 150°C$	I_{DSS}	— —	−10 −10	nAdc μAdc
Gate Reverse Current ($V_{GS} = \pm 30$ V, $V_{DS} = 0$)	I_{GSS}	—	±10	pAdc
ON CHARACTERISTICS				
Gate Threshold Voltage ($V_{DS} = -10$ V, $I_D = -10\ \mu A$)	$V_{GS(Th)}$	−1.0	−5.0	Vdc
Drain-Source On-Voltage ($I_D = -2.0$ mA, $V_{GS} = -10$ V)	$V_{DS(on)}$	—	−1.0	V
On-State Drain Current ($V_{GS} = -10$ $V_{DS} = -10$ V)	$I_{D(on)}$	−3.0	—	mA
SMALL-SIGNAL CHARACTERISTICS				
Drain-Source Resistance ($V_{GS} = -10$ V, $I_D = 0$, f = 1.0 kHz)	$r_{ds(on)}$	—	600	ohms
Forward Transfer Admittance ($V_{DS} = -10$ V, $I_D = 2.0$ mA, f = 1.0 kHz)	$\lvert y_{fs} \rvert$	1000	—	μmho
Input Capacitance ($V_{DS} = -10$ V, $V_{GS} = 0$, f = 140 kHz)	C_{iss}	—	5.0	pF
Reverse Transfer Capacitance ($V_{DS} = 0$, $V_{GS} = 0$, f = 140 kHz)	C_{rss}	—	1.3	pF
Drain-Substrate Capacitance ($V_{D(SUB)} = -10$ V, f = 140 kHz)	$C_{d(sub)}$	—	4.0	pF

SWITCHING CHARACTERISTICS

Characteristic	Conditions	Symbol	Min	Max	Unit
Turn-On Delay (Figures 5)	$I_D = -2.0$ mAdc, $V_{DS} = -10$ Vdc, $V_{GS} = -10$ V) (See Figure 9, Times Circuit Determined)	t_{d1}	—	45	ns
Rise Time (Figures 6)		t_r	—	65	ns
Turn-Off Delay (Figures 7)		t_{d2}	—	60	ns
Fall Time (Figures 8)		t_f	—	100	ns

FIGURE 1 — FOWARD TRANSFER ADMITTANCE

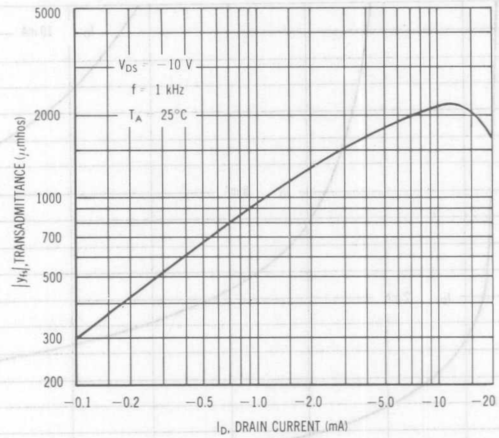


FIGURE 2 — TRANSFER CHARACTERISTICS

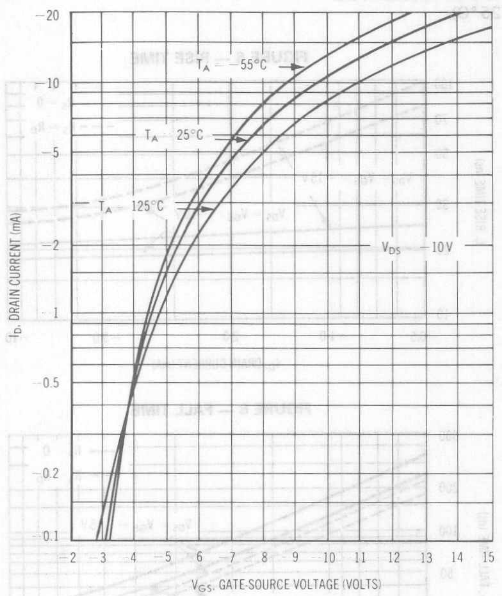
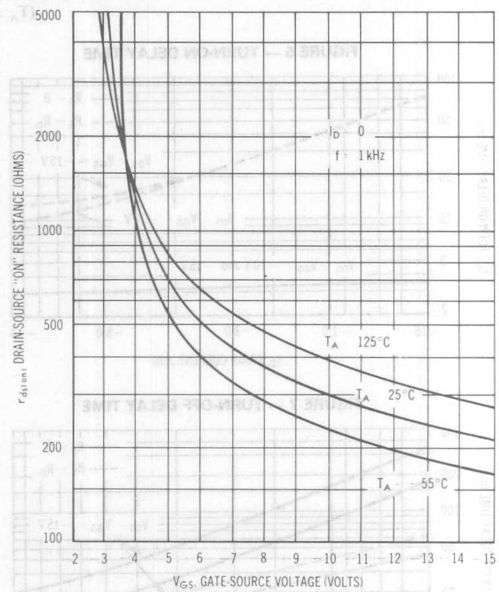
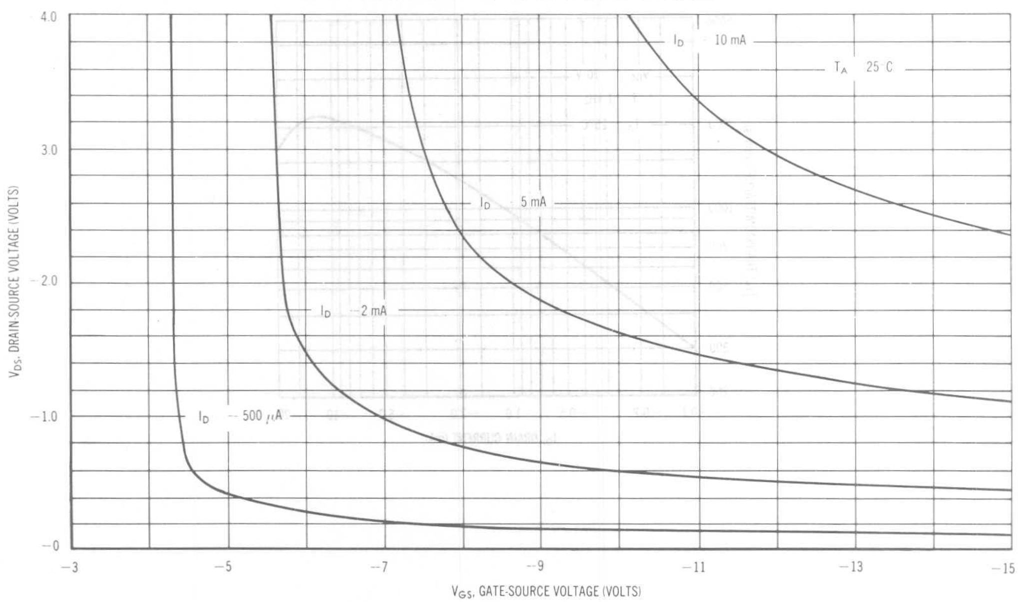


FIGURE 3 — DRAIN-SOURCE "ON" RESISTANCE



6

FIGURE 4 — "ON" DRAIN-SOURCE VOLTAGE



6

SWITCHING CHARACTERISTICS
(T_A = 25°C)

FIGURE 5 — TURN-ON DELAY TIME

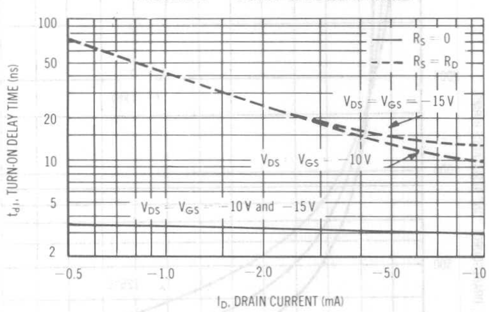


FIGURE 6 — RISE TIME

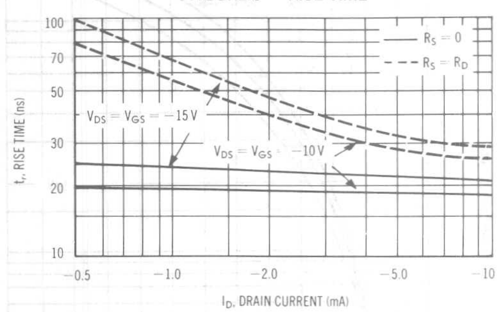


FIGURE 7 — TURN-OFF DELAY TIME

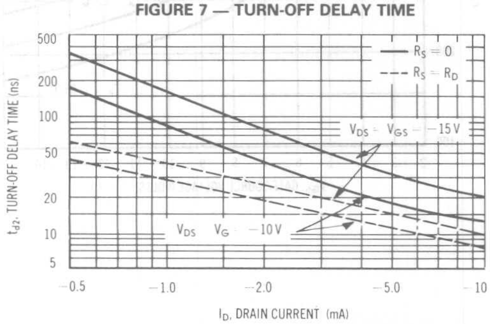


FIGURE 8 — FALL TIME

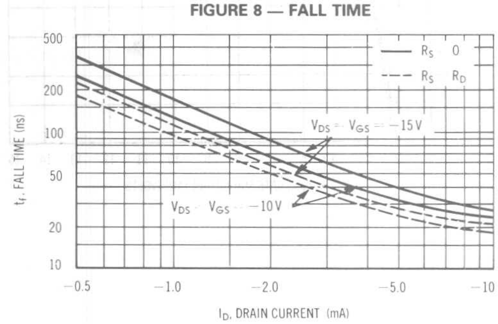
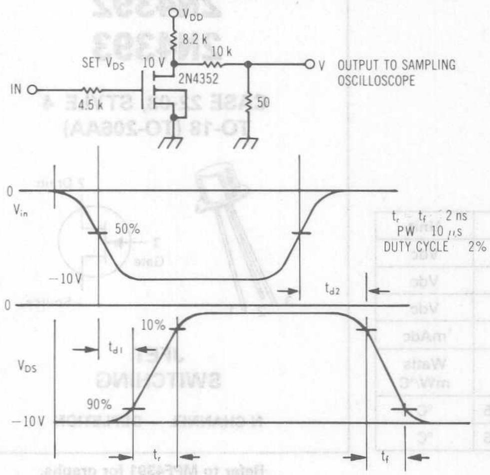


FIGURE 9 — SWITCHING CIRCUIT and WAVEFORMS



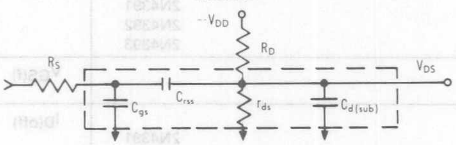
The switching characteristics shown above were measured in a test circuit similar to Figure 10. At the beginning of the switching interval, the gate voltage is at ground and the gate-source capacitance ($C_{gs} = C_{iss} - C_{rss}$) has no charge. The drain voltage is at V_{DD}, and thus the feedback capacitance (C_{rss}) is charged to V_{DD}. Similarly, the drain-substrate capacitance ($C_{d(sub)}$) is charged to V_{DD} since the substrate and source are connected to ground.

During the turn-on interval, C_{gs} is charged to V_{GS} (the input voltage) through R_S (generator impedance) (Figure 11). C_{rss} must be discharged to $V_{GS} - V_{D(on)}$ through R_S and the parallel combination of the load resistor (R_D) and the channel resistance (r_{ds}) is a function of the gate-source voltage (V_{GS}). As C_{gs} becomes charged V_{GS} is approaching V_{in} and r_{ds} decreases (see Figure 4) and since C_{rss} and $C_{d(sub)}$ are charged through r_{ds}, turn-on time is quite non-linear.

If the charging time of C_{gs} is short compared to that of C_{rss} and $C_{d(sub)}$, then r_{ds} (which is in parallel with R_D) will be low compared to R_D during the switching interval and will largely determine the turn-on time. On the other hand, during turn-off r_{ds} will be almost an open circuit requiring C_{rss} and $C_{d(sub)}$ to be charged through R_D and resulting in a turn-off time that is long compared to the turn-on time. This is especially noticeable for the curves where $R_S = 0$ and C_{gs} is charged through the pulse generator impedance only.

The switching curves shown with $R_S = R_D$ simulate the switching behavior of cascaded stages where the driving source impedance is normally the same as the load impedance. The set of curves with $R_S = 0$ simulates a low source impedance drive such as might occur in complementary logic circuits.

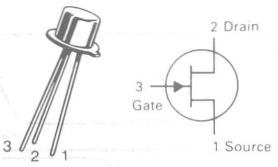
FIGURE 10 — SWITCHING CIRCUIT with MOSFET EQUIVALENT MODEL



6

2N4392
2N4393

CASE 22-03, STYLE 4
TO-18 (TO-206AA)



JFET
SWITCHING

N-CHANNEL — DEPLETION

Refer to MPF4391 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	40	Vdc
Drain-Gate Voltage	V_{DG}	40	Vdc
Gate-Source Voltage	V_{GS}	40	Vdc
Forward Gate Current	I_{GF}	50	*mAdc
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.8 10	Watts mW/°C
Operating Junction Temperature Range	T_J	−65 to +175	°C
Storage Temperature Range	T_{stg}	−65 to +175	°C

*ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = 1.0\ \mu Adc$, $V_{DS} = 0$)		$V_{(BR)GSS}$	40	—	Vdc
Gate Reverse Current ($V_{GS} = 20$ Vdc, $V_{DS} = 0$) ($V_{GS} = 20$ Vdc, $V_{DS} = 0$, $T_A = 150°C$)		I_{GSS}	 — —	 0.1 0.2	nAdc μAdc
Gate Source Voltage ($V_{DS} = 20$ Vdc, $I_D = 1.0$ nAdc)	2N4391 2N4392 2N4393	V_{GS}	4.0 2.0 0.5	10 5.0 3.0	Vdc
Gate-Source Forward Voltage ($I_G = 1.0$ mAdc, $V_{DS} = 0$)		$V_{GS(f)}$	—	1.0	Vdc
Drain-Cutoff Current ($V_{DS} = 20$ Vdc, $V_{GS} = 12$ Vdc) ($V_{DS} = 20$ Vdc, $V_{GS} = 7.0$ Vdc) ($V_{DS} = 20$ Vdc, $V_{GS} = 5.0$ Vdc) ($V_{DS} = 20$ Vdc, $V_{GS} = 12$ Vdc, $T_A = 150°C$) ($V_{DS} = 20$ Vdc, $V_{GS} = 7.0$ Vdc, $T_A = 150°C$) ($V_{DS} = 20$ Vdc, $V_{GS} = 5.0$ Vdc, $T_A = 150°C$)	 2N4391 2N4392 2N4393 2N4391 2N4392 2N4393	$I_{D(off)}$	 — — — — — —	 0.1 0.1 0.1 0.2 0.2 0.2	nAdc μAdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current(1) ($V_{DS} = 20$ Vdc, $V_{GS} = 0$)	 2N4391 2N4392 2N4393	I_{DSS}	 50 25 5.0	 150 75 30	mAdc
Drain-Source On-Voltage ($I_D = 12$ mAdc, $V_{GS} = 0$) ($I_D = 6.0$ mAdc, $V_{GS} = 0$) ($I_D = 3.0$ mAdc, $V_{GS} = 0$)	 2N4391 2N4392 2N4393	$V_{DS(on)}$	 — — —	 0.4 0.4 0.4	Vdc
Static Drain-Source On Resistance ($I_D = 1.0$ mAdc, $V_{GS} = 0$)	 2N4391 2N4392 2N4393	$r_{DS(on)}$	 — — —	 30 60 100	Ohms
SMALL-SIGNAL CHARACTERISTICS					
Drain-Source "ON" Resistance ($V_{GS} = 0$, $I_D = 0$, $f = 1.0$ kHz)	 2N4391 2N4392 2N4393	$r_{ds(on)}$	 — — —	 30 60 100	Ohms

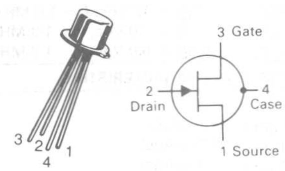
Characteristic		Symbol	Min	Max	Unit
Input Capacitance (V_{DS} = 20 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	14	pF
Reverse Transfer Capacitance (V_{DS} = 0, V_{GS} = 12 Vdc, f = 1.0 MHz) (V_{DS} = 0, V_{GS} = 7.0 Vdc, f = 1.0 MHz) (V_{DS} = 0, V_{GS} = 5.0 Vdc, f = 1.0 MHz)	 2N4391 2N4392 2N4393	C_{rss}	 — — —	 3.5 3.5 3.5	pF
SWITCHING CHARACTERISTICS					
Rise Time ($I_{D(on)}$ = 12 mAdc) ($I_{D(on)}$ = 6.0 mAdc) ($I_{D(on)}$ = 3.0 mAdc)	 2N4391 2N4392 2N4393	t_r	 — — —	 5.0 5.0 5.0	ns
Fall Time ($V_{GS(off)}$ = 12 Vdc) ($V_{GS(off)}$ = 7.0 Vdc) ($V_{GS(off)}$ = 5.0 Vdc)	 2N4391 2N4392 2N4393	t_f	 — — —	 15 20 30	ns
Turn-On Time ($I_{D(on)}$ = 12 mAdc) ($I_{D(on)}$ = 6.0 mAdc) ($I_{D(on)}$ = 3.0 mAdc)	 2N4391 2N4392 2N4393	t_{on}	 — — —	 15 15 15	ns
Turn-Off Time ($V_{GS(off)}$ = 12 Vdc) ($V_{GS(off)}$ = 7.0 Vdc) ($V_{GS(off)}$ = 5.0 Vdc)	 2N4391 2N4392 2N4393	t_{off}	 — — —	 20 35 50	ns

(1) Pulse Test: Pulse Width $\leqslant$ 100 μs, Duty Cycle $\leqslant$ 1.0%.
*In addition to JEDEC Registered Data.

6

2N4416,A

CASE 20-03, STYLE 1
TO-72 (TO-206AF)



JFET
VHF/UHF AMPLIFIER

N-CHANNEL — DEPLETION

JAN JTX JTXV AVAILABLE

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	30	Vdc
Drain-Gate Voltage	2N4416 2N4416A	V_{DG}	30 35	Vdc
Gate-Source Voltage		V_{GS}	30	Vdc
Gate Current		I_G	10	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C		P_D	300 1.71	mW mW/°C
Operating and Storage Junction Temperature Range		T_J, T_{stg}	−65 to +175	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = 1.0\ \mu Adc$, $V_{DS} = 0$)	 2N4416 2N4416A	$V_{(BR)GSS}$	 30 35	 — —	Vdc
Gate Reverse Current ($V_{GS} = 20$ Vdc, $V_{DS} = 0$) ($V_{GS} = 20$ Vdc, $V_{DS} = 0$, $T_A = +150°C$)		I_{GSS}	 — —	 100 200	pAdc
Gate Source Cutoff Voltage ($I_D = 1.0$ nAdc, $V_{DS} = 15$ Vdc)		$V_{GS(off)}$	—	6.0	Vdc
Gate Source Voltage ($I_D = 0.5$ mAdc, $V_{DS} = 15$ Vdc)		V_{GS}	1.0	5.5	Vdc
Gate-Source Forward Voltage ($I_G = 1.0$ mAdc, $V_{DS} = 0$)		$V_{GS(f)}$	—	1.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current(1) ($V_{DS} = 15$ Vdc, $V_{GS} = 0$)		I_{DSS}	5.0	15	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance(1) ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 1.0 kHz)		$\|y_{fs}\|$	4500	7500	μmhos
Real Part of Forward Transfer Admittance ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 400 MHz)		$y_{fs(real)}$	4000	—	μmhos
Real Part of Input Admittance ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 100 MHz) ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 400 MHz)		$y_{is(real)}$	 — —	 100 1000	μmhos
Output Admittance ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 1.0 kHz)		$\|y_{os}\|$	—	50	μmhos
Real Part of Output Admittance ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 100 MHz) ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 400 MHz)		$y_{os(real)}$	 — —	 75 100	μmhos
Imaginary Part of Input Admittance ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 100 MHz) ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 400 MHz)		$y_{is(imag)}$	 — —	 2500 10,000	μmhos
Imaginary Part of Output Admittance ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 100 MHz) ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 400 MHz)		$y_{os(imag)}$	 — —	 1000 4000	μmhos

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Input Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	4.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{rss}	—	0.8	pF
Common Source Output Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{oss}	—	2.0	pF
FUNCTIONAL CHARACTERISTICS				
Noise Figure (Figures 3 and 4)	NF			dB
(V_{DS} = 15 Vdc, I_D = 5.0 mAdc, $R_g \approx$ 1000 Ohms, f = 100 MHz)		—	2.0	
(V_{DS} = 15 Vdc, I_D = 5.0 mAdc, $R_g \approx$ 1000 Ohms, f = 400 MHz)		—	4.0	
Small-Signal Power Gain Common Source (Figure 1)	G_{ps}			dB
(V_{DS} = 15 Vdc, I_D = 5.0 mAdc, f = 100 MHz)		18	—	
(V_{DS} = 15 Vdc, I_D = 5.0 mAdc, f = 400 MHz)		10	—	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 1.0%.

POWER GAIN

FIGURE 1 — EFFECTS OF DRAIN CURRENT

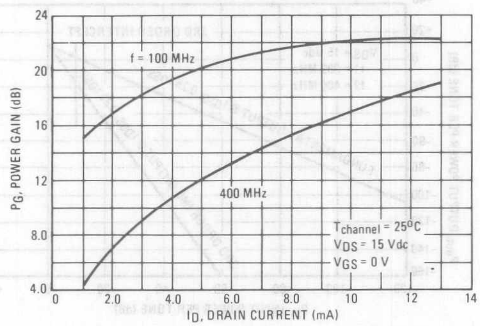
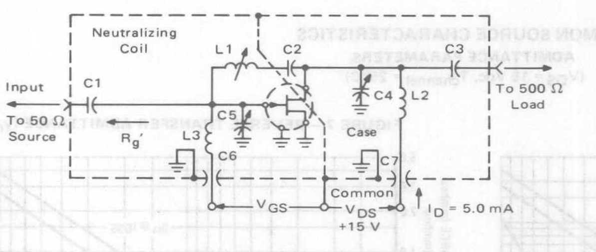


FIGURE 2 — 100 MHz and 400 MHz NEUTRALIZED TEST CIRCUIT



Reference Designation	VALUE	
	100 MHz	400 MHz
C1	7.0 pF	1.8 pF
C2	1000 pF	17 pF
C3	3.0 pF	1.0 pF
C4	1-12 pF	0.8-8.0 pF
C5	1-12 pF	0.8-8.0 pF
C6	0.0015 μF	0.001 μF
C7	0.0015 μF	0.001 μF
L1	3.0 μH*	0.2 μH**
L2	0.15 μH*	0.03 μH**
L3	0.14 μH*	0.022 μH**

Adjust V_{GS} for I_D = 50 mA
V_{GS} < 0 Volts

NOTE: The noise source is a hot-cold body (AIL type 70 or equivalent) with a test receiver (AIL type 136 or equivalent).

*L1 17 turns, (approx. — depends upon circuit layout) AWG #28 enameled copper wire, close wound on 9/32" ceramic coil form. Tuning provided by a powdered iron slug.
L2 4-1/2 turns, AWG #18 enameled copper wire, 5/16" long, 3/8" I.D. (AIR CORE).
L3 3-1/2 turns, AWG #18 enameled copper wire, 1/4" long, 3/8" I.D. (AIR CORE).

**L1 6 turns, (approx. — depends upon circuit layout) AWG #24 enameled copper wire, close wound on 7/32" ceramic coil form. Tuning provided by an aluminum slug.
L2 1 turn, AWG #16 enameled copper wire, 3/8" I.D. (AIR CORE).
L3 1/2 turn, AWG #16 enameled copper wire, 1/4" I.D. (AIR CORE).

NOISE FIGURE

($T_{channel}$ = 25°C)

FIGURE 3 – EFFECTS OF DRAIN-SOURCE VOLTAGE

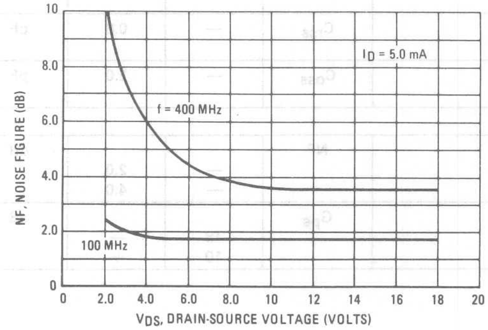
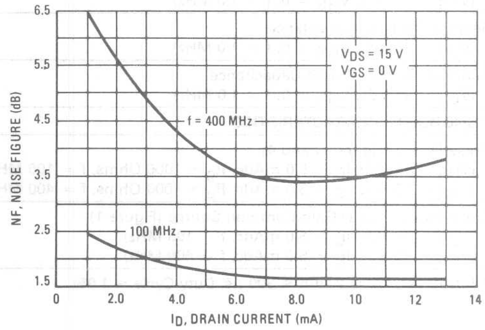


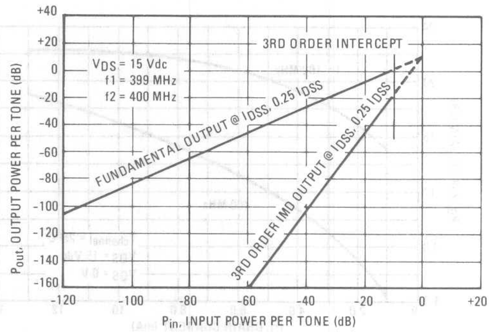
FIGURE 4 – EFFECTS OF DRAIN CURRENT



6

INTERMODULATION CHARACTERISTICS

FIGURE 5 – THIRD ORDER INTERMODULATION DISTORTION



COMMON SOURCE CHARACTERISTICS

ADMITTANCE PARAMETERS

(V_{DS} = 15 Vdc, $T_{channel}$ = 25°C)

FIGURE 6 – INPUT ADMITTANCE (y_{is})

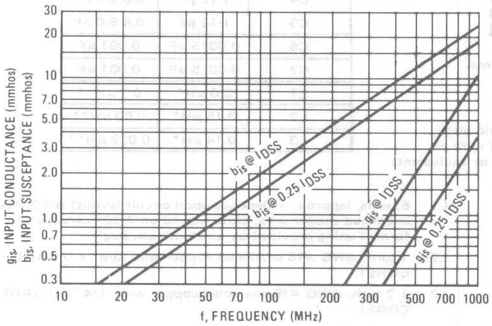
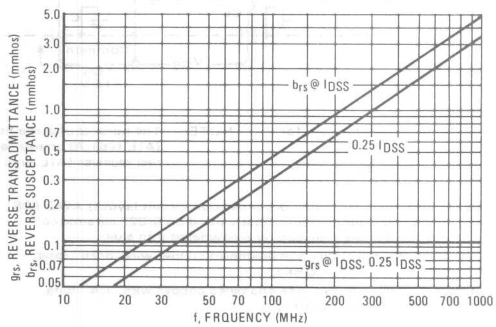
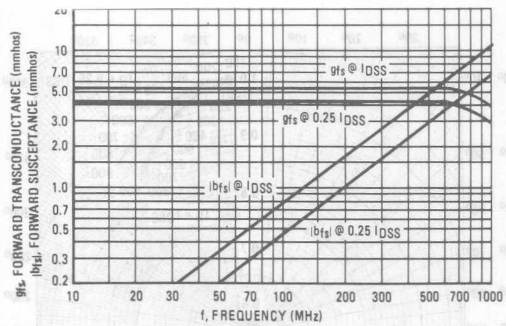
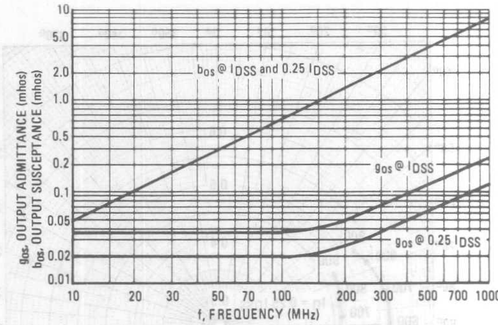


FIGURE 7 – REVERSE TRANSFER ADMITTANCE (y_{rs})







6

COMMON SOURCE CHARACTERISTICS
S-PARAMETERS
(V_{DS} = 15 Vdc, $T_{channel}$ = 25°C,
Data Points in MHz)

FIGURE 10 – S_{11s}

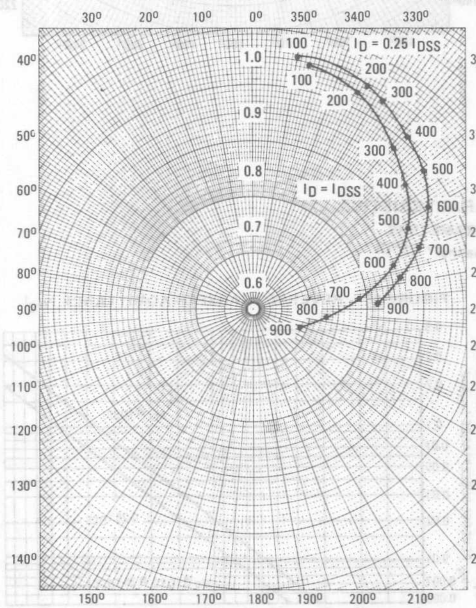


FIGURE 11 – S_{12s}

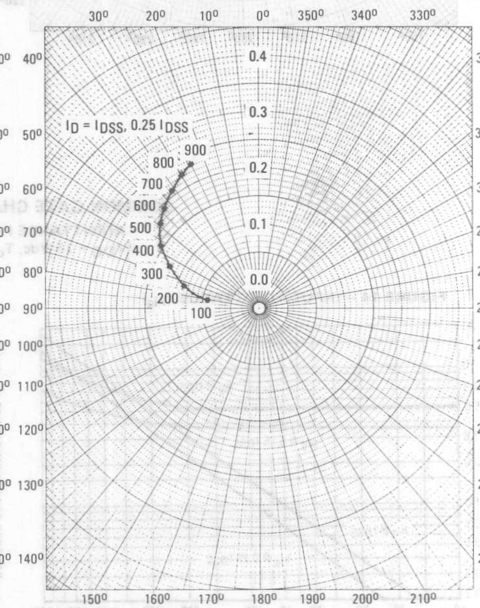


FIGURE 12 – S_{21s}

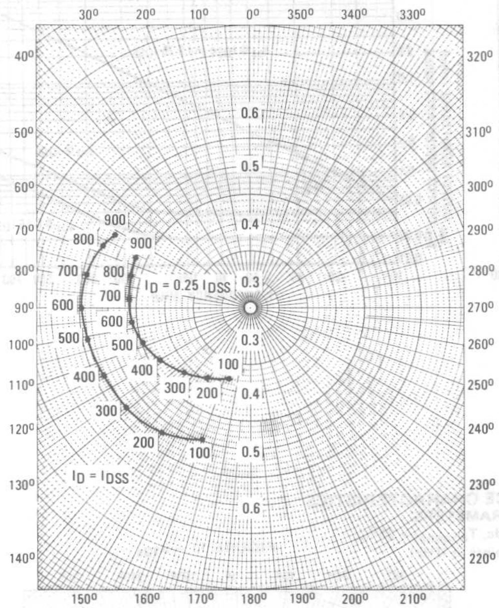
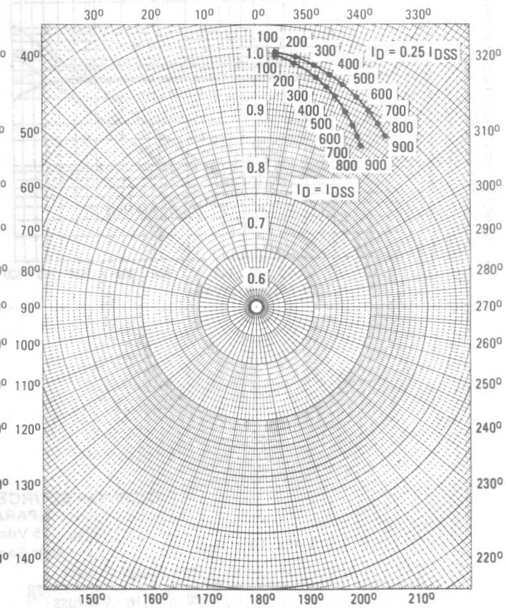


FIGURE 13 – S_{22s}



COMMON GATE CHARACTERISTICS
ADMITTANCE PARAMETERS
(V_{DG} = 15 Vdc, $T_{channel}$ = 25°C)

FIGURE 14 – INPUT ADMITTANCE (y_{ig})

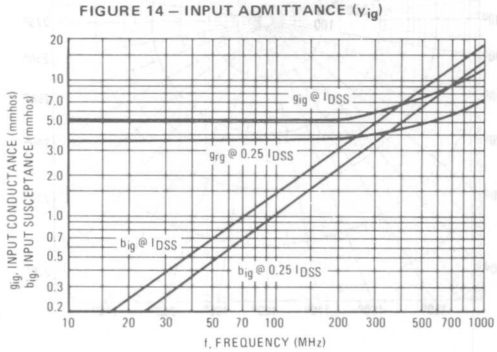


FIGURE 15 – REVERSE TRANSFER ADMITTANCE (y_{rg})

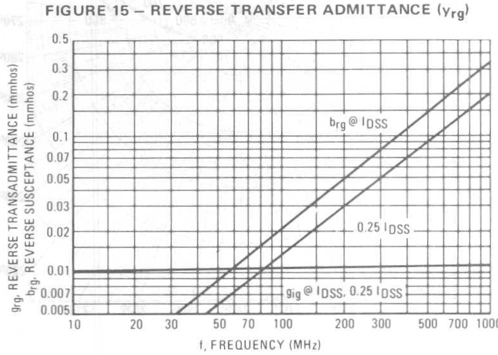


FIGURE 16 – FORWARD TRANSFER ADMITTANCE (y_{fg})

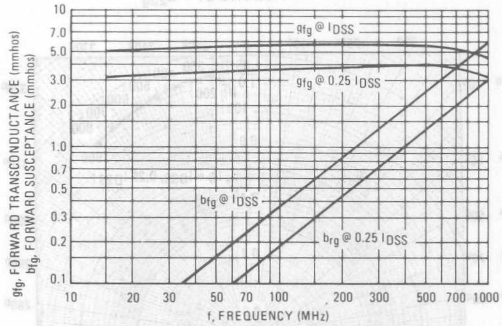
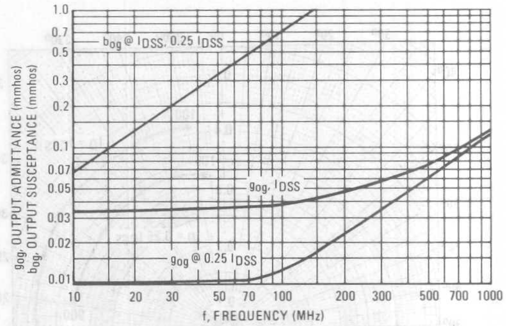


FIGURE 17 – OUTPUT ADMITTANCE (y_{og})



COMMON GATE CHARACTERISTICS

S-PARAMETERS

(V_{DG} = 15 Vdc, $T_{channel}$ = 25°C, Data Points in MHz)

FIGURE 18 – S_{11g}

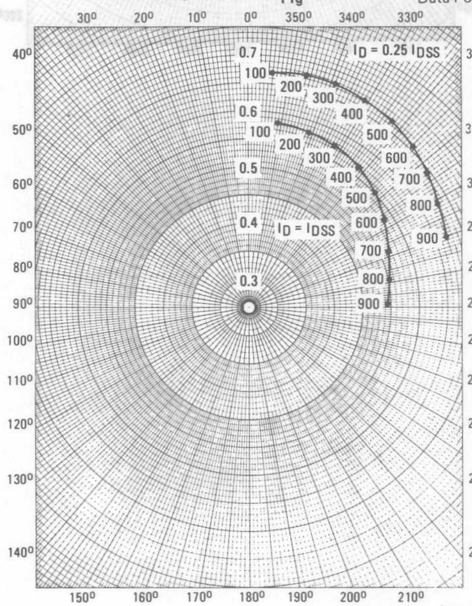


FIGURE 19 – S_{12g}

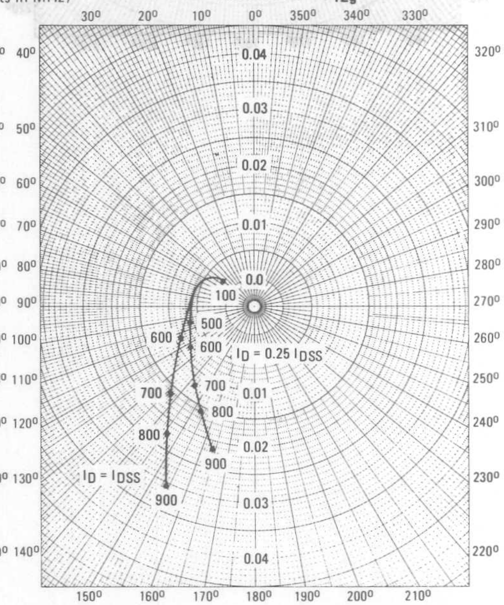


FIGURE 20 — S_{21g}

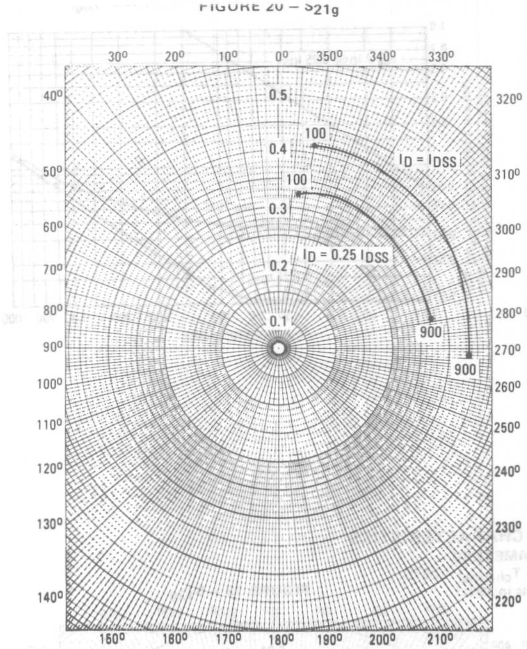
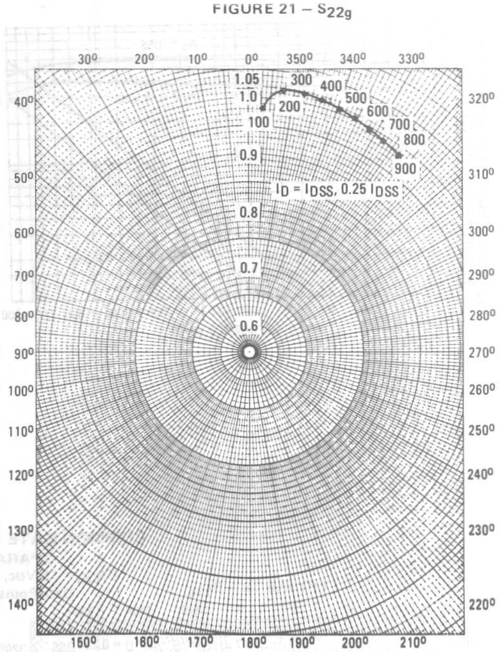


FIGURE 21 — S_{22g}

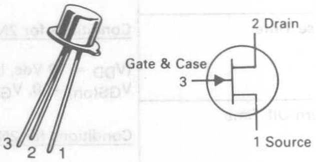


6

thru

2N4861,A

JAN, JTX AVAILABLE
CASE 22-03, STYLE 4
TO-18 (TO-206AA)



JFET
SWITCHING

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	2N4856,A 2N4857,A 2N4858,A	2N4859,A 2N4860,A 2N4861,A	Unit
Drain-Source Voltage	V_{DS}	+40	+30	Vdc
Drain-Gate Voltage	V_{DG}	+40	+30	Vdc
Reverse Gate-Source Voltage	V_{GSR}	−40	−30	Vdc
Forward Gate Current	I_{GF}	50		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	360 2.4		mW mW/°C
Storage Temperature Range	T_{stg}	−65 to +175		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = 1.0 μAdc, V_{DS} = 0)	2N4856,A, 2N4857,A, 2N4858,A 2N4859,A, 2N4860,A, 2N4861,A	$V_{(BR)GSS}$	−40 −30	— —	Vdc
Gate Reverse Current (V_{GS} = −20 Vdc, V_{DS} = 0) (V_{GS} = −15 Vdc, V_{DS} = 0) (V_{GS} = −20 Vdc, V_{DS} = 0, T_A = 150°C) (V_{GS} = −15 Vdc, V_{DS} = 0, T_A = 150°C)	 2N4856,A 2N4857,A, 2N4858,A 2N4859,A, 2N4860,A, 2N4861,A 2N4856,A, 2N4857,A, 2N4858,A 2N4859,A, 2N4860,A, 2N4861,A	I_{GSS}	 — — — —	 0.25 0.25 0.5 0.5	 nAdc μAdc
Gate Source Cutoff Voltage (V_{DS} = 15 Vdc, I_D = 0.5 nAdc)	2N4856,A, 2N4859,A 2N4857,A, 2N4860,A 2N4858,A, 2N4861,A	$V_{GS(off)}$	−4.0 −2.0 −0.8	−10 −6.0 −4.0	Vdc
Drain Cutoff Current (V_{DS} = 15 Vdc, V_{GS} = −10 Vdc) (V_{DS} = 15 Vdc, V_{GS} = −10 Vdc, T_A = 150°C)		$I_{D(off)}$	 — —	 0.25 0.5	 nAdc μAdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current(1) (V_{DS} = 15 Vdc, V_{GS} = 0)	 2N4856,A, 2N4859,A 2N4857,A, 2N4860,A 2N4858,A, 2N4861,A	I_{DSS}	 50 20 8.0	 — 100 80	mAdc
Drain-Source On-Voltage (I_D = 20 mAdc, V_{GS} = 0) (I_D = 10 mAdc, V_{GS} = 0) (I_D = 5.0 mAdc, V_{GS} = 0)	 2N4856,A, 2N4859,A 2N4857,A, 2N4860,A 2N4858,A, 2N4861,A	$V_{DS(on)}$	 — — —	 0.75 0.5 0.5	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Drain-Source "ON" Resistance (V_{GS} = 0, I_D = 0, f = 1.0 kHz)	2N4856,A, 2N4859,A 2N4857,A, 2N4860,A 2N4858,A, 2N4861,A	$r_{ds(on)}$	— — —	25 40 60	Ohms
Input Capacitance (V_{DS} = 0, V_{GS} = −10 Vdc, f = 1.0 MHz)	2N4856 thru 2N4861 2N4856A thru 2N4861A	C_{iss}	— —	18 10	pF
Reverse Transfer Capacitance (V_{DS} = 0, V_{GS} = −10 Vdc, f = 1.0 MHz)	2N4856 thru 2N4861 2N4856A, 2N4859A 2N4857A, 2N4858A, 2N4860A, 2N4861A	C_{rss}	— — —	8.0 4.0 3.5	pF

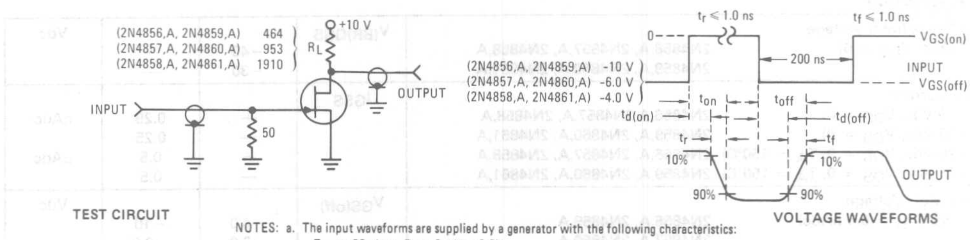
6

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic			Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS (See Figure 1) (2)						
Turn-On Delay Time	Conditions for 2N4856,A, 2N4859,A:	2N4856, 2N4859	$t_{d(on)}$	—	6.0	ns
		2N4856A, 2N4859A		—	5.0	
	(V_{DD} = 10 Vdc, $I_{D(on)}$ = 20 mAdc,	2N4857, 2N4860		—	6.0	
	$V_{GS(on)}$ = 0, $V_{GS(off)}$ = −10 Vdc)	2N4857A, 2N4860A		—	6.0	
		2N4858, 2N4861		—	10	
		2N4858A, 2N4861A		—	8.0	
Rise Time	Conditions for 2N4857,A, 2N4860,A:	2N4856,A, 2N4859,A	t_r	—	3.0	ns
		2N4857,A, 2N4860,A		—	4.0	
	(V_{DD} = 10 Vdc, $I_{D(on)}$ = 10 mAdc,	2N4858, 2N4861		—	10	
	$V_{GS(on)}$ = 0, $V_{GS(off)}$ = −6.0 Vdc)	2N4858A, 2N4861A		—	8.0	
Turn-Off Time		2N4856, 2N4859	t_{off}	—	25	
	Conditions for 2N4858,A, 2N4861,A:	2N4856A, 2N4859A		—	20	ns
		2N4857, 2N4860		—	50	
	(V_{DD} = 10 Vdc, $I_{D(on)}$ = 5.0 mAdc,	2N4857A, 2N4860A		—	40	
	$V_{GS(on)}$ = 0, $V_{GS(off)}$ = −4.0 Vdc)	2N4858, 2N4861		—	100	
		2N4858A; 2N4861A		—	80	

(1) Pulse Test: Pulse Width = 100 ms, Duty Cycle ≤ 10%.
(2) The $I_{D(on)}$ values are nominal; exact values vary slightly with transistor parameters.

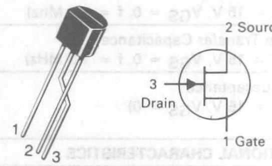
FIGURE 1 – SWITCHING TIMES TEST CIRCUIT



NOTES: a. The input waveforms are supplied by a generator with the following characteristics: Z_{out} = 50 ohms, Duty Cycle ≈ 2.0%.
b. Waveforms are monitored on an oscilloscope with the following characteristics: t_r ≤ 0.75 ns, R_{in} ≥ 1.0 megohm, C_{in} ≤ 2.5 pF.

2N5245
2N5246
2N5247

CASE 29-04, STYLE 23
TO-92 (TO-226AA)



JFET
HIGH-FREQUENCY
AMPLIFIER

N-CHANNEL — DEPLETION

Refer to 2N4416 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage	V_{GS}	−30	Vdc
Gate Current	I_G	50	mA
Total Device Dissipation @ T_A = 25°C Derate above 25°C (Free Air)	P_D	360 2.88	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	500 4.0	mW mW/°C
Lead Temperature (1/16″ from Case for 10 Seconds)	T_L	260	°C
Storage Temperature Range	T_{stg}	−65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = −1.0 μA, V_{DS} = 0)		$V_{(BR)GSS}$	−30	—	Vdc
Gate Reverse Current (V_{GS} = −20 V, V_{DS} = 0)		I_{GSS}	—	−1.0	nA
Gate 1 Leakage Current (V_{G1S} = −20 V, V_{DS} = 0, T_A = 100°C)		I_{G1SS}	—	−0.5	μA
Gate Source Cutoff Voltage (V_{DS} = 15 V, I_D = 10 mA)	 2N5245 2N5246 2N5247	$V_{GS(off)}$	 −1.0 −0.5 −1.5	 −6.0 −4.0 −8.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current (V_{DS} = 15 V, V_{GS} = 0, Pulsed: See Note 1)	 2N5245 2N5246 2N5247	I_{DSS}	 5.0 1.5 8.0	 15 7.0 24	mA
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance (V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz)	 2N5245 2N5246 2N5247	$\|y_{fs}\|$	 4500 3000 4500	 7500 6000 8000	μmhos
Input Admittance (V_{DS} = 15 V, V_{GS} = 0)	 (100 MHz) (400 MHz)	$Re(y_{is})$	 — —	 100 1000	μmhos
Output Admittance (V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz)	 2N5245 2N5246 2N5247	$\|y_{os}\|$	 — — —	 50 50 70	μmhos
Output Conductance (V_{DS} = 15 V, V_{GS} = 0)	 2N5245 (100 MHz) 2N5246 2N5247 2N5245 (400 MHz) 2N5246 2N5247	$Re(y_{os})$	 — — — — — —	 75 75 100 100 100 150	μmhos

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

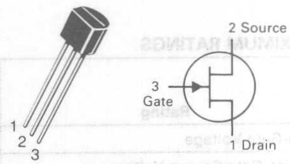
Characteristic		Symbol	Min	Max	Unit
Forward Transconductance (V_{DS} = 15 V, V_{GS} = 0, f = 400 MHz)	 2N5245 2N5246 2N5247	$Re(y_{fs})$	 4000 2500 4000	 — — —	µmhos
Input Capacitance (V_{DS} = 15 V, V_{GS} = 0, f = 1.0 Mhz)		C_{iss}	—	4.5	pF
Reverse Transfer Capacitance (V_{DS} = 15 V, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	—	1.0	pF
Input Susceptance (V_{DS} = 15 V, V_{GS} = 0)	 (100 MHz) (400 MHz)	$I_M(Yis)$	 — —	 3.0 12.0	mmho
FUNCTIONAL CHARACTERISTICS					
Noise Figure (V_{DS} = 15 V, I_D = 5.0 mA, R'_G = 1.0 kΩ)		NF	 — —	 2.0 4.0	dB
Common Source Power Gain (V_{DS} = 15 V, I_D = 5.0 mA, R'_G = 1.0 kΩ)	 2N5245 (100 MHz) 2N5245 (400 MHz)	G_{ps}	 18 10	 — —	dB
Output Susceptance (V_{DS} = 15 V, V_{GS} = 0)	 (100 MHz) (400 MHz)	$I_M(Yos)$	 — —	 1000 4000	µmho

Note 1: tp = 100 ms, Duty Cycle = 10%.

6

2N5458
2N5459

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
GENERAL PURPOSE

N-CHANNEL — DEPLETION

Refer to 2N4220 for graphs.

6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG}	25	Vdc
Reverse Gate-Source Voltage	V_{GSR}	−25	Vdc
Gate Current	I_G	10	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	310 2.82	mW mW/°C
Junction Temperature Range	T_J	125	°C
Storage Channel Temperature Range	T_{stg}	−65 to +150	°C

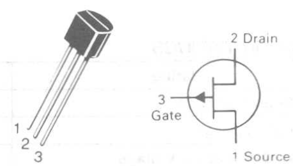
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Gate-Source Breakdown Voltage ($I_G = -10\ \mu Adc$, $V_{DS} = 0$)		$V_{(BR)GSS}$	−25	—	—	Vdc
Gate Reverse Current ($V_{GS} = -15$ Vdc, $V_{DS} = 0$) ($V_{GS} = -15$ Vdc, $V_{DS} = 0$, $T_A = 100°C$)		I_{GSS}	 — —	 — —	 −1.0 −200	nAdc
Gate Source Cutoff Voltage ($V_{DS} = 15$ Vdc, $I_D = 10$ nAdc)	2N5457 2N5458 2N5459	$V_{GS(off)}$	−0.5 −1.0 −2.0	— — —	−6.0 −7.0 −8.0	Vdc
Gate Source Voltage ($V_{DS} = 15$ Vdc, $I_D = 100\ \mu Adc$) ($V_{DS} = 15$ Vdc, $I_D = 200\ \mu Adc$) ($V_{DS} = 15$ Vdc, $I_D = 400\ \mu Adc$)	 2N5457 2N5458 2N5459	V_{GS}	 — — —	 −2.5 −3.5 −4.5	 — — —	Vdc
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current* ($V_{DS} = 15$ Vdc, $V_{GS} = 0$)	2N5457 2N5458 2N5459	I_{DSS}	1.0 2.0 4.0	3.0 6.0 9.0	5.0 9.0 16	mAdc
SMALL-SIGNAL CHARACTERISTICS						
Forward Transfer Admittance Common Source* ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 1.0 kHz)	2N5457 2N5458 2N5459	$\lvert y_{fs} \rvert$	1000 1500 2000	 — 	5000 5500 6000	μmhos
Output Admittance Common Source* ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 1.0 kHz)		$\lvert y_{os} \rvert$	—	10	50	μmhos
Input Capacitance ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 1.0 MHz)		C_{iss}	—	4.5	7.0	pF
Reverse Transfer Capacitance ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 1.0 MHz)		C_{rss}	—	1.5	3.0	pF

*Pulse Test: Pulse Width ≤ 630 ms; Duty Cycle ≤ 10%.

2N5460
thru
2N5465

CASE 29-04, STYLE 7
TO-92 (TO-226AA)



JFET
AMPLIFIER

P-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	2N5460 2N5461 2N5462	2N5463 2N5464 2N5465	Unit
Drain-Gate Voltage	V_{DG}	40	60	Vdc
Reverse Gate-Source Voltage	V_{GSR}	40	60	Vdc
Forward Gate Current	$I_{G(f)}$	10		mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	310 2.82		mW mW/°C
Junction Temperature Range	T_J	−65 to +135		°C
Storage Channel Temperature Range	T_{stg}	−65 to +150		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Gate-Source Breakdown Voltage (I_G = 10 μAdc, V_{DS} = 0)	 2N5460, 2N5461, 2N5462 2N5463, 2N5464, 2N5465	$V_{(BR)GSS}$	 40 60	 — —	 — —	Vdc
Gate Reverse Current (V_{GS} = 20 Vdc, V_{DS} = 0) (V_{GS} = 30 Vdc, V_{DS} = 0) (V_{GS} = 20 Vdc, V_{DS} = 0, T_A = 100°C) (V_{GS} = 30 Vdc, V_{DS} = 0, T_A = 100°C)	 2N5460, 2N5461, 2N5462 2N5463, 2N5464, 2N5465 2N5460, 2N5461, 2N5462 2N5463, 2N5464, 2N5465	I_{GSS}	 — — — —	 — — — —	 5.0 5.0 1.0 1.0	 nAdc μAdc
Gate Source Cutoff Voltage (V_{DS} = 15 Vdc, I_D = 1.0 μAdc)	 2N5460, 2N5463 2N5461, 2N5464 2N5462, 2N5465	$V_{GS(off)}$	 0.75 1.0 1.8	 — — —	 6.0 7.5 9.0	Vdc
Gate Source Voltage (V_{DS} = 15 Vdc, I_D = 0.1 mAdc) (V_{DS} = 15 Vdc, I_D = 0.2 mAdc) (V_{DS} = 15 Vdc, I_D = 0.4 mAdc)	 2N5460, 2N5463 2N5461, 2N5464 2N5462, 2N5465	V_{GS}	 0.5 0.8 1.5	 — — —	 4.0 4.5 6.0	Vdc
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)	 2N5460, 2N5463 2N5461, 2N5464 2N5462, 2N5465	I_{DSS}	 1.0 2.0 4.0	 — — —	 5.0 9.0 16	mAdc
SMALL-SIGNAL CHARACTERISTICS						
Forward Transfer Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)	 2N5460, 2N5463 2N5461, 2N5464 2N5462, 2N5465	$\|y_{fs}\|$	 1000 1500 2000	 — — —	 4000 5000 6000	μmhos
Output Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)		$\|y_{os}\|$	—	—	75	μmhos
Input Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	5.0	7.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	—	1.0	2.0	pF
FUNCTIONAL CHARACTERISTICS						
Noise Figure (V_{DS} = 15 Vdc, V_{GS} = 0, R_G = 1.0 Megohm, f = 100 Hz, BW = 1.0 Hz)		NF	—	1.0	2.5	dB
Equivalent Short-Circuit Input Noise Voltage (V_{DS} = 15 Vdc, V_{GS} = 0, f = 100 Hz, BW = 1.0 Hz)		e_n	—	60	115	nV/$\sqrt{Hz}$

DRAIN CURRENT versus GATE SOURCE VOLTAGE

FIGURE 1 — $V_{GS(off)}$ = 2.0 VOLTS

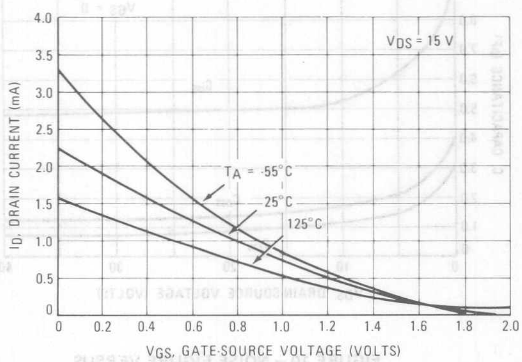


FIGURE 2 — $V_{GS(off)}$ = 4.0 VOLTS

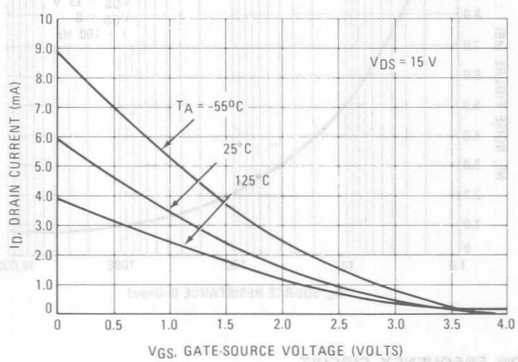
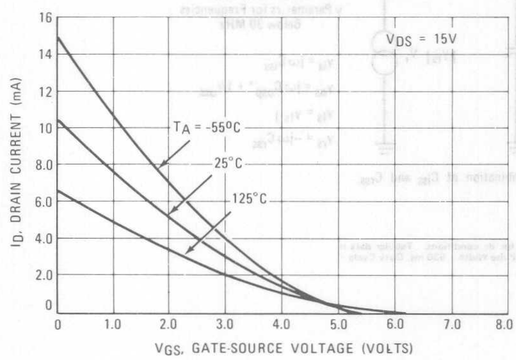


FIGURE 3 — $V_{GS(off)}$ = 5.0 VOLTS



FORWARD TRANSFER ADMITTANCE versus DRAIN CURRENT

FIGURE 4 — $V_{GS(off)}$ = 2.0 VOLTS

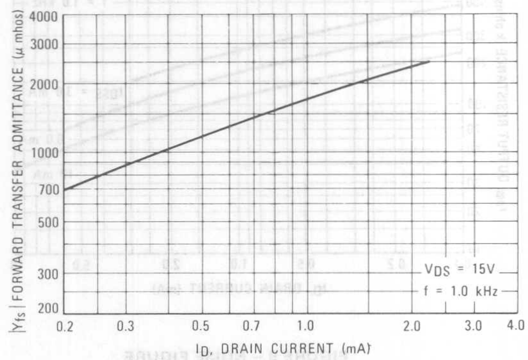


FIGURE 5 — $V_{GS(off)}$ = 4.0 VOLTS

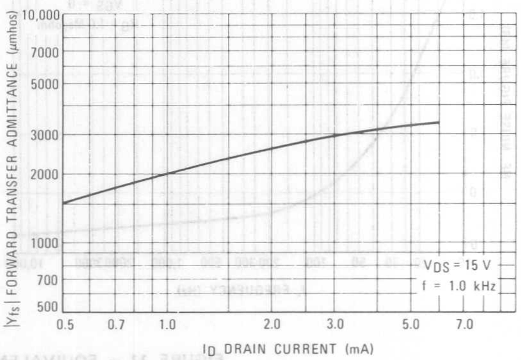
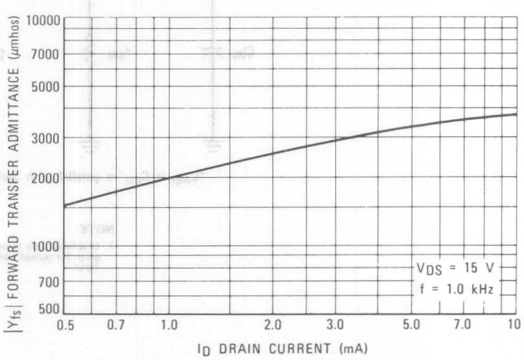
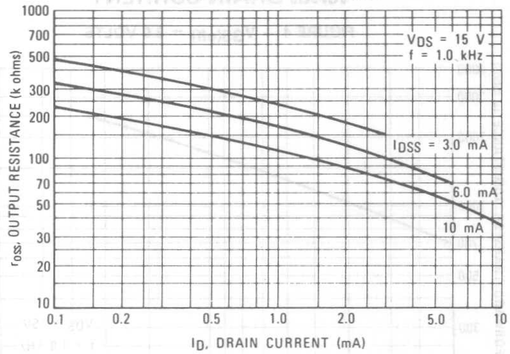


FIGURE 6 — $V_{GS(off)}$ = 5.0 VOLTS



6

VERSUS DRAIN CURRENT



DRAIN-SOURCE VOLTAGE

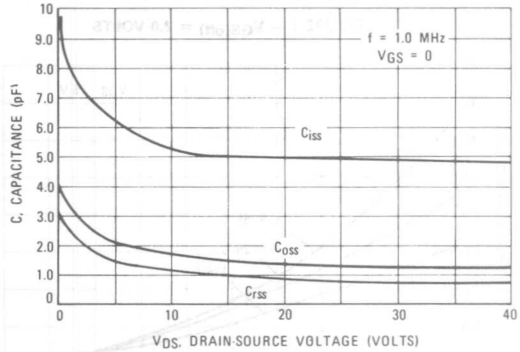


FIGURE 9 – NOISE FIGURE VERSUS FREQUENCY

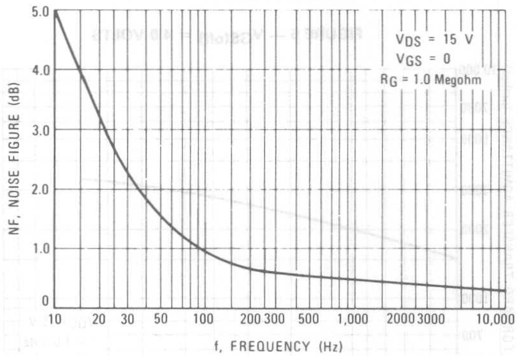


FIGURE 10 – NOISE FIGURE VERSUS SOURCE RESISTANCE

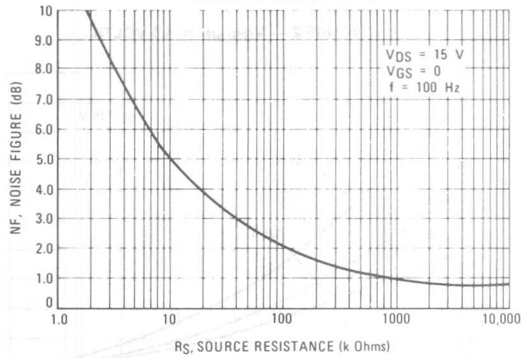
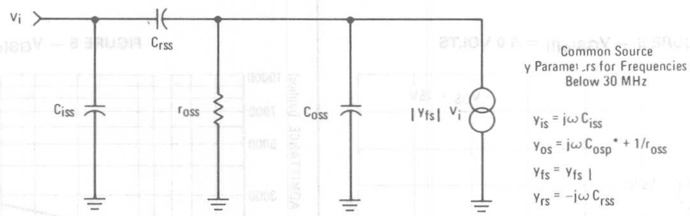


FIGURE 11 – EQUIVALENT LOW FREQUENCY CIRCUIT



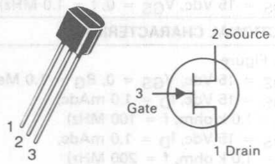
*C_{osp} is C_{oss} in parallel with Series Combination of C_{iss} and C_{rss}.

NOTE:
1. Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%).

thru

2N5486

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
VHF/UHF AMPLIFIER

N-CHANNEL — DEPLETION

Refer to 2N4416 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V_{DG}	25	Vdc
Reverse Gate-Source Voltage	V_{GSR}	25	Vdc
Drain Current	I_D	30	mAdc
Forward Gate Current	$I_{G(f)}$	10	mAdc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	310 2.82	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Gate-Source Breakdown Voltage (I_G = −1.0 μAdc, V_{DS} = 0)		$V_{(BR)GSS}$	−25	—	—	Vdc
Gate Reverse Current (V_{GS} = −20 Vdc, V_{DS} = 0) (V_{GS} = −20 Vdc, V_{DS} = 0, T_A = 100°C)		I_{GSS}	 — —	 — —	 −1.0 −0.2	 nAdc μAdc
Gate Source Cutoff Voltage (V_{DS} = 15 Vdc, I_D = 10 nAdc)	 2N5484 2N5485 2N5486	$V_{GS(off)}$	 −0.3 −0.5 −2.0	 — — —	 −3.0 −4.0 −6.0	Vdc
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current (V_{DS} = 15 Vdc, V_{GS} = 0)	 2N5484 2N5485 2N5486	I_{DSS}	 1.0 4.0 8.0	 — — —	 5.0 10 20	mAdc
SMALL-SIGNAL CHARACTERISTICS						
Forward Transfer Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)	 2N5484 2N5485 2N5486	$\|y_{fs}\|$	 3000 3500 4000	 — — —	 6000 7000 8000	μmhos
Input Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 100 MHz) (V_{DS} = 15 Vdc, V_{GS} = 0, f = 400 MHz)	 2N5484 2N5485, 2N5486	$Re(y_{is})$	 — —	 — —	 100 1000	μmhos
Output Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)	 2N5484 2N5485 2N5486	$\|y_{os}\|$	 — — —	 — — —	 50 60 75	μmhos
Output Conductance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 100 MHz) (V_{DS} = 15 Vdc, V_{GS} = 0, f = 400 MHz)	 2N5484 2N5485, 2N5486	$Re(y_{os})$	 — —	 — —	 75 100	μmhos
Forward Transconductance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 100 MHz) (V_{DS} = 15 Vdc, V_{GS} = 0, f = 400 MHz)	 2N5484 2N5485 2N5486	$Re(y_{fs})$	 2500 3000 3500	 — — —	 — — —	μmhos

6

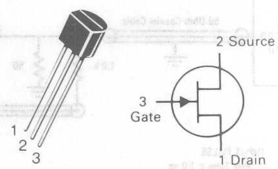
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
Input Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	—	5.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	—	—	1.0	pF
Output Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{oss}	—	—	2.0	pF
FUNCTIONAL CHARACTERISTICS						
Noise Figure		NF				dB
(V_{DS} = 15 Vdc, V_{GS} = 0, R_G = 1.0 Megohm, f = 1.0 kHz)			—	—	2.5	
(V_{DS} = 15 Vdc, I_D = 1.0 mAdc, $R_G \approx$ 1.0 k ohm, f = 100 MHz)	2N5484		—	—	3.0	
(V_{DS} = 15 Vdc, I_D = 1.0 mAdc, $R_G \approx$ 1.0 k ohm, f = 200 MHz)	2N5484		—	4.0	—	
(V_{DS} = 15 Vdc, I_D = 4.0 mAdc, $R_G \approx$ 1.0 k ohm, f = 100 MHz)	2N5485, 2N5486		—	—	2.0	
(V_{DS} = 15 Vdc, I_D = 4.0 mAdc, $R_G \approx$ 1.0 k ohm, f = 400 MHz)	2N5485, 2N5486		—	—	4.0	
Common Source Power Gain		G_{ps}				dB
(V_{DS} = 15 Vdc, I_D = 1.0 mAdc, f = 100 MHz)	2N5484		16	—	25	
(V_{DS} = 15 Vdc, I_D = 1.0 mAdc, f = 200 MHz)	2N5484		—	14	—	
(V_{DS} = 15 Vdc, I_D = 4.0 mAdc, f = 100 MHz)	2N5485, 2N5486		18	—	30	
(V_{DS} = 15 Vdc, I_D = 4.0 mAdc, f = 400 MHz)	2N5485, 2N5486		10	—	20	

6

2N5555

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
SWITCHING

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG}	25	Vdc
Gate-Source Voltage	V_{GS}	25	Vdc
Forward Gate Current	I_{GF}	10	mAdc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	310 2.82	mW mW/°C
Junction Temperature Range	T_J	−65 to +150	°C
Storage Temperature Range	T_{stg}	−65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

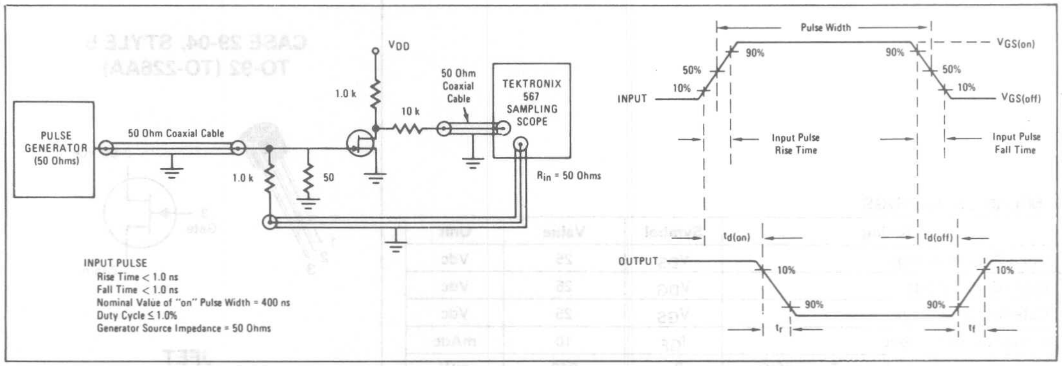
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage (I_G = 10 μAdc, V_{DS} = 0)	$V_{(BR)GSS}$	25	—	Vdc
Gate Reverse Current (V_{GS} = 15 Vdc, V_{DS} = 0)	I_{GSS}	—	1.0	nAdc
Drain Cutoff Current (V_{DS} = 12 Vdc, V_{GS} = −10 V) (V_{DS} = 12 Vdc, V_{GS} = −10 V, T_A = 100°C)	$I_{D(off)}$	 — —	 10 2.0	nAdc μAdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current* (V_{DS} = 15 Vdc, V_{GS} = 0)	I_{DSS}	15	—	mAdc
Gate-Source Forward Voltage ($I_{G(f)}$ = 1.0 mAdc, V_{DS} = 0)	$V_{GS(f)}$	—	1.0	Vdc
Drain-Source On-Voltage (I_D = 7.0 mAdc, V_{GS} = 0)	$V_{DS(on)}$	—	1.5	Vdc
Static Drain-Source On Resistance (I_D = 0.1 mAdc, V_{GS} = 0)	$r_{DS(on)}$	—	150	Ohms
SMALL-SIGNAL CHARACTERISTICS				
Small-Signal Drain-Source "ON" Resistance (V_{GS} = 0, I_D = 0, f = 1.0 kHz)	$r_{ds(on)}$	—	150	Ohms
Input Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	5.0	pF
Reverse Transfer Capacitance (V_{DS} = 0, V_{GS} = 10 Vdc, f = 1.0 MHz)	C_{rss}	—	1.2	pF

SWITCHING CHARACTERISTICS

Characteristic	Conditions	Symbol	Min	Max	Unit
Turn-On Delay Time	(V_{DD} = 10 Vdc, $I_{D(on)}$ = 7.0 mAdc,	$t_{d(on)}$	—	5.0	ns
Rise Time	$V_{GS(on)}$ = 0, $V_{GS(off)}$ = −10 Vdc) (See Figure 1)	t_r	—	5.0	ns
Turn-Off Delay Time	(V_{DD} = 10 Vdc, $I_{D(on)}$ = 7.0 mAdc,	$t_{d(off)}$	—	15	ns
Fall Time	$V_{GS(on)}$ = 0, $V_{GS(off)}$ = −10 Vdc) (See Figure 1)	t_f	—	10	ns

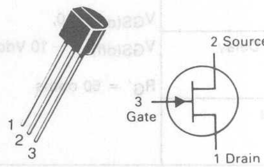
*Pulse Test: Pulse Width < 300 μs, Duty Cycle < 3.0%.

FIGURE 1 — SWITCHING TIMES TEST CIRCUIT



2N5640

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
SWITCHING

N-CHANNEL — DEPLETION

Refer to 2N5653 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Reverse Gate-Source Voltage	V_{GSR}	30	Vdc
Forward Gate Current	I_{GF}	10	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	310 2.82	mW mW/°C
Junction Temperature Range	T_J	−65 to +150	°C
Storage Temperature Range	T_{stg}	−65 to +150	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = 10\ \mu Adc$, $V_{DS} = 0$)		$V_{(BR)GSS}$	30	—	Vdc
Gate Reverse Current ($V_{GS} = -15$ Vdc, $V_{DS} = 0$) ($V_{GS} = -15$ Vdc, $V_{DS} = 0$, $T_A = 100°C$)		I_{GSS}	 — —	 1.0 1.0	 nAdc μAdc
Drain Cutoff Current ($V_{DS} = 15$ Vdc, $V_{GS} = -12$ Vdc) ($V_{DS} = 15$ Vdc, $V_{GS} = -8.0$ Vdc) ($V_{DS} = 15$ Vdc, $V_{GS} = -6.0$ Vdc) ($V_{DS} = 15$ Vdc, $V_{GS} = -12$ Vdc, $T_A = 100°C$) ($V_{DS} = 15$ Vdc, $V_{GS} = -8.0$ Vdc, $T_A = 100°C$) ($V_{DS} = 15$ Vdc, $V_{GS} = -6.0$ Vdc, $T_A = 100°C$)	 2N5638 2N5639 2N5640 2N5638 2N5639 2N5640	$I_{D(off)}$	 — — — — — —	 1.0 1.0 1.0 1.0 1.0 1.0	 nAdc μAdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current(1) ($V_{DS} = 20$ Vdc, $V_{GS} = 0$)	 2N5638 2N5639 2N5640	I_{DSS}	 50 25 5.0	 — — —	mAdc
Drain-Source On-Voltage ($I_D = 12$ mAdc, $V_{GS} = 0$) ($I_D = 6.0$ mAdc, $V_{GS} = 0$) ($I_D = 3.0$ mAdc, $V_{GS} = 0$)	 2N5638 2N5639 2N5640	$V_{DS(on)}$	 — — —	 0.5 0.5 0.5	Vdc
Static Drain-Source On Resistance ($I_D = 1.0$ mAdc, $V_{GS} = 0$)	 2N5638 2N5639 2N5640	$r_{DS(on)}$	 — — —	 30 60 100	Ohms
SMALL-SIGNAL CHARACTERISTICS					
Static Drain-Source "ON" Resistance ($V_{GS} = 0$, $I_D = 0$, f = 1.0 kHz)	 2N5638 2N5639 2N5640	$r_{ds(on)}$	 — — —	 30 60 100	Ohms
Input Capacitance ($V_{DS} = 0$, $V_{GS} = -12$ Vdc, f = 1.0 MHz)		C_{iss}	—	10	pF
Reverse Transfer Capacitance ($V_{DS} = 0$, $V_{GS} = -12$ Vdc, f = 1.0 MHz)		C_{rss}	—	4.0	pF

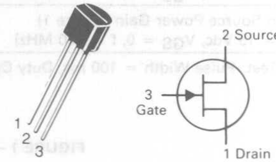
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic				Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS							
Turn-On Delay Time	V_{DD} = 10 Vdc, $V_{GS(on)}$ = 0, $V_{GS(off)}$ = −10 Vdc, R_G' = 50 ohms	$I_{D(on)}$ = 12 mAdc	2N5638	$t_{d(on)}$	—	4.0	ns
		6.0 mAdc	2N5639		—	6.0	
		3.0 mAdc	2N5640		—	8.0	
Rise Time		$I_{D(on)}$ = 12 mAdc	2N5638	t_r	—	5.0	ns
		6.0 mAdc	2N5639		—	8.0	
		3.0 mAdc	2N5640		—	10	
Turn-Off Delay Time		$I_{D(on)}$ = 12 mAdc	2N5638	$t_{d(off)}$	—	5.0	ns
		6.0 mAdc	2N5639		—	10	
		3.0 mAdc	2N5640		—	15	
Fall Time		$I_{D(on)}$ = 12 mAdc	2N5638	t_f	—	10	ns
		6.0 mAdc	2N5639		—	20	
		3.0 mAdc	2N5640		—	30	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 3.0%.

2N5668
2N5669
2N5670

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
VHF AMPLIFIER

N-CHANNEL — DEPLETION

6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG}	25	Vdc
Reverse Gate-Source Voltage	V_{GSR}	25	Vdc
Drain Current	I_D	20	mAdc
Forward Gate Current	$I_{G(f)}$	10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	310 2.82	mW mW/°C
Storage Channel Temperature Range	T_{stg}	−65 to +150	°C

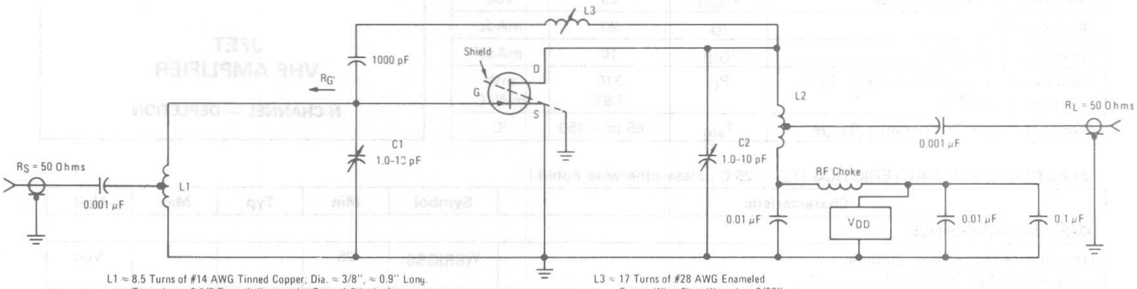
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Gate-Source Breakdown Voltage (I_G = 10 μAdc, V_{DS} = 0)		$V_{(BR)GSS}$	25	—	—	Vdc
Gate Reverse Current (V_{GS} = −15 Vdc, V_{DS} = 0) (V_{GS} = −15 Vdc, V_{DS} = 0, T_A = 100°C)		I_{GSS}	 — —	 — —	 2.0 2.0	 nAdc μAdc
Gate Source Cutoff Voltage (V_{DS} = 15 Vdc, I_D = 10 nAdc)	 2N5668 2N5669 2N5670	$V_{GS(off)}$	 0.2 1.0 2.0	 — — —	 4.0 6.0 8.0	Vdc
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current(1) (V_{DS} = 15 Vdc, V_{GS} = 0)	 2N5668 2N5669 2N5670	I_{DSS}	 1.0 4.0 8.0	 — — —	 5.0 10 20	mAdc
SMALL-SIGNAL CHARACTERISTICS						
Forward Transfer Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)	 2N5668 2N5669 2N5670	$\|y_{fs}\|$	 1500 2000 3000	 — — —	 6500 6500 7500	μmhos
Input Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 100 MHz)		$Re(y_{is})$	—	125	800	μmhos
Output Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)	 2N5668 2N5669 2N5670	$\|y_{os}\|$	 — — —	 — — —	 20 50 75	μmhos
Output Conductance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 100 MHz)	 2N5668 2N5669 2N5670	$Re(y_{os})$	 — — —	 10 25 35	 50 100 150	μmhos
Forward Transconductance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 100 MHz)	 2N5668 2N5669 2N5670	$Re(y_{fs})$	 1000 1600 2500	 — — —	 — — —	μmhos
Input Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	4.7	7.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	—	1.0	3.0	pF

Output Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{oss}	—	1.4	4.0	pF
FUNCTIONAL CHARACTERISTICS					
Noise Figure (Figure 1) (V_{DS} = 15 Vdc, V_{GS} = 0, f = 100 MHz at R_G' = 1.0 k ohm)	NF	—	—	2.5	dB
Common Source Power Gain (Figure 1) (V_{DS} = 15 Vdc, V_{GS} = 0, f = 100 MHz)	G_{ps}	16	—	—	dB

(1) Pulse Test: Pulse Width = 100 ms, Duty Cycle ≤ 10%.

FIGURE 1 — 100 MHz, POWER GAIN AND NOISE FIGURE TEST CIRCUIT



L1 ≈ 8.5 Turns of #14 AWG Tinned Copper; Dia. ≈ 3/8″, ≈ 0.9″ Long. Tapped at ≈ 2-1/2 Turns (adjust to give R_G = 1.0 k ohm); Parallel Resistance = 40 k ohms; tunes at ≈ 8.0 pF.

L2 ≈ 13.5 Turns #16 AWG Tinned Copper; Dia. ≈ 3/8″, ≈ 1.2″ Long. Tapped at ≈ 5 Turns; Parallel Resistance = 40 k ohms; tunes at ≈ 4.0 pF.

L3 ≈ 17 Turns of #28 AWG Enameled Copper Wire, Close Wound on 9/32″ Ceramic Form, Tuning Provided by a Powdered Iron Slug.

6

MAXIMUM RATINGS

Rating	Symbol	2N6659 MPF6659	2N6660 MPF6660	2N6661 MPF6661	Unit
Drain-Source Voltage	V_{DS}	35	60	90	Vdc
Drain-Gate Voltage	V_{DG}	35	60	90	Vdc
Gate-Source Voltage	V_{GS}		± 30		Vdc
Drain Current — Continuous (1) Pulsed (2)	I_D I_{DM}		2.0 3.0		Adc
		2N6659 2N6660 2N6661		MPF6659 MPF6660 MPF6661	
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	6.25 50		2.5 20	Watts mW/°C
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	— —		1.0 8.0	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−55 to +150		°C

(1) The Power Dissipation of the package may result in a lower continuous drain current.
(2) Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2N6659
2N6660
2N6661
MPF6659
MPF6660
MPF6661

2N6659,60,61
CASE 79-02, STYLE 6
TO-39 (TO-205AD)

MPF6659,60,61
CASE 29-03, STYLE 22
TO-226AE

TMOS
SWITCHING TRANSISTOR
N-CHANNEL — ENHANCEMENT

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Zero-Gate-Voltage Drain Current (V_{DS} = Maximum Rating, V_{GS} = 0)		I_{DSS}	—	—	10	μAdc
Gate-Body Leakage Current (V_{GS} = 15 V, V_{DS} = 0)		I_{GSS}	—	—	100	nAdc
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 10 μA)	2N6659, MPF6659 2N6660, MPF6660 2N6661, MPF6661	$V_{(BR)DSX}$	35 60 90	— — —	— — —	Vdc
ON CHARACTERISTICS(1)						
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.0 mA)		$V_{GS(Th)}$	0.8	1.4	2.0	Vdc
Drain-Source On-Voltage (V_{GS} = 10 V, I_D = 1.0 A)	2N6659, MPF6659 2N6660, MPF6660 2N6661, MPF6661	$V_{DS(on)}$	— — —	— — —	1.8 3.0 4.0	Vdc
(V_{GS} = 5.0 V, I_D = 0.3 A)	2N6659, MPF6659 2N6660, MPF6660 2N6661, MPF6661		— — —	0.8 0.9 0.9	1.5 1.5 1.6	
Static Drain-Source On Resistance (V_{GS} = 10 Vdc, I_D = 1.0 Adc)	2N6659, MPF6659 2N6660, MPF6660 2N6661, MPF6661	$r_{DS(on)}$	— — —	— — —	1.8 3.0 4.0	Ohms
On-State Drain Current (V_{DS} = 25 V, V_{GS} = 10 V)		$I_{D(on)}$	1.0	2.0	—	Amps
SMALL-SIGNAL CHARACTERISTICS						
Input Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	30	50	pF
Reverse Transfer Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	—	3.6	10	pF
Output Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{oss}	—	20	40	pF
Forward Transconductance (V_{DS} = 25 V, I_D = 0.5 A)		g_{fs}	170	—	—	mmhos

6

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS(1)					
Rise Time	t_r	—	—	5.0	ns
Fall Time	t_f	—	—	5.0	ns
Turn-On Time	t_{on}	—	—	5.0	ns
Turn-Off Time	t_{off}	—	—	5.0	ns

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

RESISTIVE SWITCHING

FIGURE 1 — SWITCHING TEST CIRCUIT

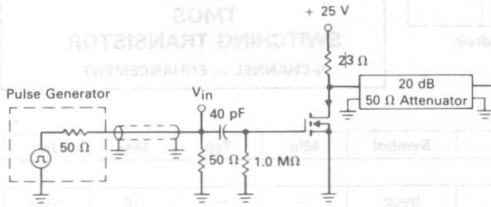


FIGURE 2 — SWITCHING WAVEFORMS

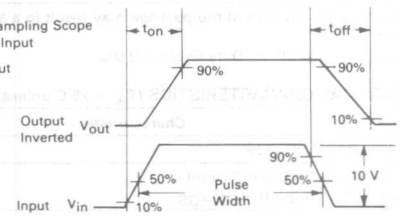


FIGURE 3 — $V_{GS(th)}$ NORMALIZED versus TEMPERATURE

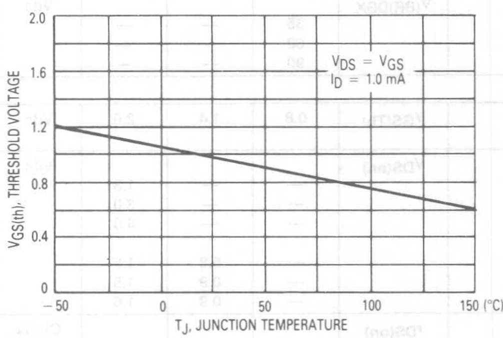


FIGURE 4 — ON-REGION CHARACTERISTICS

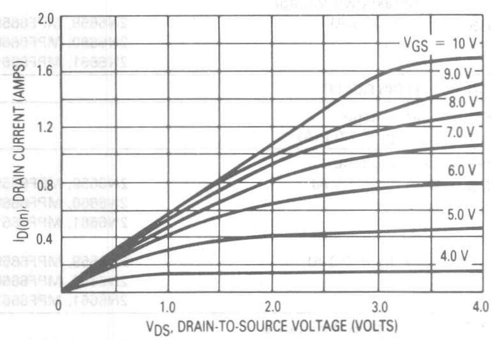


FIGURE 5 — OUTPUT CHARACTERISTICS

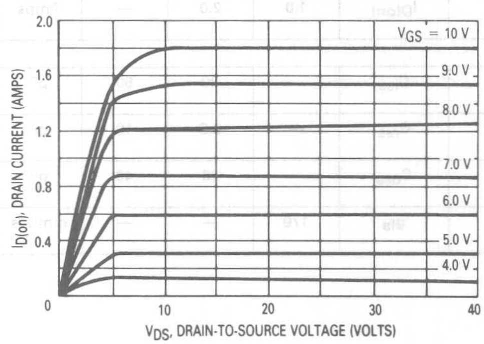


FIGURE 6 — CAPACITANCE versus DRAIN-TO-SOURCE VOLTAGE

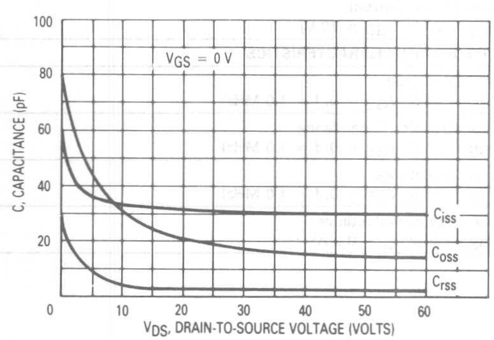
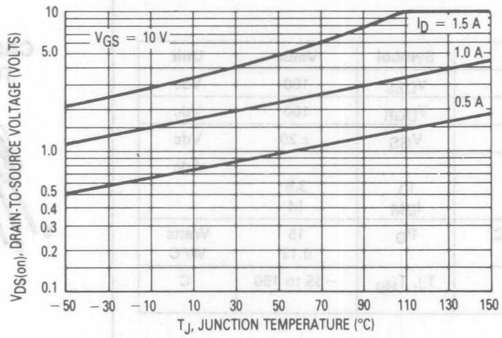


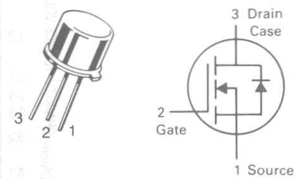
FIGURE 7 — ON-VOLTAGE versus TEMPERATURE



6

2N6782

CASE 79-03, STYLE 6
TO-39 (TO-205AF)



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	100	Vdc
Drain-Gate Voltage (R_{GS} = 1.0 mΩ)	V_{DGR}	100	Vdc
Gate-Source Voltage	V_{GS}	±20	Vdc
Drain Current Continuous Pulsed	 I_D I_{DM}	 3.5 14	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	15 0.12	Watts W/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150	°C

THERMAL CHARACTERISTICS

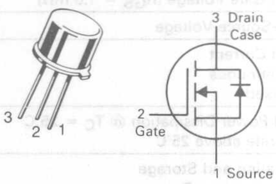
Thermal Resistance Junction to Case	$R_{\theta JC}$	8.33	°C/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	175	°C/W
Maximum Lead Temperature 1.6 mm from Case for 10 s	T_L	300	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 0.25 mA)	$V_{(BR)DSS}$	100	—	Vdc
Zero Gate Voltage Drain Current (V_{DS} = 100 V, V_{GS} = 0 V) (V_{DS} = 80 V, V_{GS} = 0 V, T_J = 125°C)	I_{DSS}	 — —	 250 1000	μAdc
Gate-Body Leakage Current, Forward (V_{GS} = 20 Vdc, V_{DS} = 0)	I_{GSSF}	—	100	nAdc
Gate-Body Leakage Current, Reverse (V_{GS} = −20 Vdc, V_{DS} = 0)	I_{GSSR}	—	−100	nAdc
ON CHARACTERISTICS*				
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 0.5 mA)	$V_{GS(th)}$	2.0	4.0	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 2.25 Adc) T_A = 25°C T_A = 125°C	$r_{DS(on)}$	— —	0.6 1.08	Ohm
Drain-Source On-Voltage (V_{GS} = 10 V, I_D = 3.5 Adc)	$V_{DS(on)}$	—	2.1	Vdc
Forward Transconductance (V_{DS} = 5.0 V, I_D = 2.25 Adc)	g_{fs}	1.0	3.0	mhos
DYNAMIC CHARACTERISTICS				
Input Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	60	200	pF
Output Capacitance	C_{oss}	40	100	
Reverse Transfer Capacitance	C_{rss}	10	25	
SWITCHING CHARACTERISTICS*				
Turn-On Delay Time (V_{DD} ≈ 34 V, I_D = 2.25 Rated I_D, R_{gen} = 50 ohms)	$t_{d(on)}$	—	15	ns
Rise Time	t_r	—	25	
Turn-Off Delay Time	$t_{d(off)}$	—	25	
Fall Time	t_f	—	20	
SOURCE-DRAIN DIODE CHARACTERISTICS*				
Diode Forward Voltage (I_S = Rated $I_{D(on)}$, V_{GS} = 0)	V_{SD}	0.75	1.5	Vdc
Forward Turn-On Time	t_{on}	—	Negligible	ns
Reverse Recovery Time	t_{rr}	—	200	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

CASE 79-03, STYLE 6
TO-39 (TO-205AF)



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	200	Vdc
Drain-Gate Voltage (R_{GS} = 1.0 mΩ)	V_{DGR}	200	Vdc
Gate-Source Voltage	V_{GS}	±20	Vdc
Drain Current Continuous Pulsed	 I_D I_{DM}	 2.25 9.0	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	15 0.12	Watts W/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Case	$R_{\theta JC}$	8.33	°C/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	175	°C/W
Maximum Lead Temperature 1.6 mm from Case for 10 s	T_L	300	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

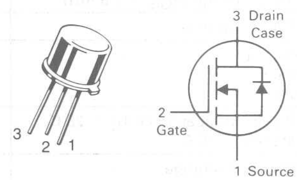
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 0.25 mA)		$V_{(BR)DSS}$	200		Vdc
Zero Gate Voltage Drain Current (V_{DS} = Rated V_{DSS}, V_{GS} = 0) (V_{DS} = 0.8 Rated V_{DSS}, V_{GS} = 0, T_J = 125°C)		I_{DSS}	 — —	 250 1000	μAdc
Gate-Body Leakage Current, Forward (V_{GS} = 20 Vdc, V_{DS} = 0)		I_{GSSF}		100	nAdc
Gate-Body Leakage Current, Reverse (V_{GS} = −20 Vdc, V_{DS} = 0)		I_{GSSR}		−100	nAdc
ON CHARACTERISTICS*					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 0.5 mA)		$V_{GS(th)}$	2.0	4.0	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 1.5 Adc)	T_A = 25°C T_A = 125°C	$r_{DS(on)}$	 —	1.5 2.81	Ohm
Drain-Source On-Voltage (V_{GS} = 10 V, I_D = 2.25 Adc)		$V_{DS(on)}$	—	3.37	Vdc
Forward Transconductance (V_{DS} = 5.0 V, I_D = 1.5 Adc)		g_{fs}	0.9	2.7	mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	60	200	pF
Output Capacitance		C_{oss}	20	80	
Reverse Transfer Capacitance		C_{rss}	5.0	25	
SWITCHING CHARACTERISTICS*					
Turn-On Delay Time	(V_{DD} = 75 V, I_D = 1.5 A, R_{gen} = 50 ohms)	$t_{d(on)}$	—	15	ns
Rise Time		t_r	—	20	
Turn-Off Delay Time		$t_{d(off)}$	—	30	
Fall Time		t_f	—	20	
SOURCE-DRAIN DIODE CHARACTERISTICS*					
Diode Forward Voltage	(I_S = Rated $I_{D(on)}$, V_{GS} = 0)	V_{SD}	0.7	1.5	Vdc
Forward Turn-On Time		t_{on}	—	Negligible	ns
Reverse Recovery Time		t_{rr}	290 (Typ)	—	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

6

2N6788

CASE 79-03, STYLE 6
TO-39 (TO-205AF)



TMOS FET
TRANSISTOR

N-CHANNEL — ENHANCEMENT

6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	100	Vdc
Drain-Gate Voltage (R_{GS} = 1.0 mΩ)	V_{DGR}	100	Vdc
Gate-Source Voltage	V_{GS}	±20	Vdc
Drain Current Continuous Pulsed	 I_D I_{DM}	 6.0 24	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	20 0.16	Watts W/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Case	$R_{\theta JC}$	6.25	°C/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	175	°C/W
Maximum Lead Temperature 1.6 mm from Case for 10 s	T_L	300	°C

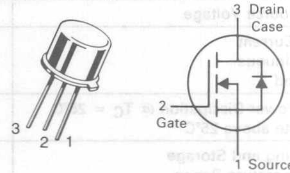
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 0.25 mA)		$V_{(BR)DSS}$	100	—	Vdc
Zero Gate Voltage Drain Current (V_{DS} = Rated V_{DSS}, V_{GS} = 0) (V_{DS} = 80 V, V_{GS} = 0, T_J = 125°C)		I_{DSS}	 — —	 1.0 4.0	mA
Gate-Body Leakage Current, Forward (V_{GS} = 20 Vdc, V_{DS} = 0)		I_{GSSF}	—	100	nAdc
Gate-Body Leakage Current, Reverse (V_{GS} = −20 Vdc, V_{DS} = 0)		I_{GSSR}	—	−100	nAdc
ON CHARACTERISTICS*					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.0 mA)		$V_{GS(th)}$	2.0	4.0	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 3.5 Adc)	T_A = 25°C T_A = 125°C	$r_{DS(on)}$	— —	0.3 0.54	Ohm
Drain-Source On-Voltage (V_{GS} = 10 V, I_D = 6.0 Adc)		$V_{DS(on)}$	—	1.8	Vdc
Forward Transconductance (V_{DS} = 5.0 V, I_D = 3.5 Adc)		g_{fs}	1.5	4.5	mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	200	600	pF
Output Capacitance		C_{oss}	100	400	
Reverse Transfer Capacitance		C_{rss}	20	100	
SWITCHING CHARACTERISTICS*					
Turn-On Delay Time	(V_{DD} ≈ 35 V, I_D = 3.5 A, R_{gen} = 50 ohms)	$t_{d(on)}$	—	40	ns
Rise Time		t_r	—	70	
Turn-Off Delay Time		$t_{d(off)}$	—	40	
Fall Time		t_f	—	70	
SOURCE-DRAIN DIODE CHARACTERISTICS*					
Diode Forward Voltage	(I_S = Rated $I_{D(on)}$, V_{GS} = 0)	V_{SD}	0.8	1.8	Vdc
Forward Turn-On Time		t_{on}	—	Negligible	ns
Reverse Recovery Time		t_{rr}	—	230	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2N6790

CASE 79-03, STYLE 6
TO-39 (TO-205AF)



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	200	Vdc
Drain-Gate Voltage (R_{GS} = 1.0 mΩ)	V_{DGR}	200	Vdc
Gate-Source Voltage	V_{GS}	±20	Vdc
Drain Current Continuous Pulsed	 I_D I_{DM}	 3.5 14	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	20 0.16	Watts W/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Case	$R_{\theta JC}$	6.25	°C/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	175	°C/W
Maximum Lead Temperature 1.6 mm from Case for 10 s	T_L	300	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 0.25 mA)		$V_{(BR)DSS}$	200	—	Vdc
Zero Gate Voltage Drain Current (V_{DS} = Rated V_{DSS}, V_{GS} = 0) (V_{DS} = 0.8 Rated V_{DSS}, V_{GS} = 0, T_J = 125°C)		I_{DSS}	 — —	 250 1000	μAdc
Gate-Body Leakage Current, Forward (V_{GS} = 20 Vdc, V_{DS} = 0)		I_{GSSF}	—	100	nAdc
Gate-Body Leakage Current, Reverse (V_{GS} = −20 Vdc, V_{DS} = 0)		I_{GSSR}	—	−100	nAdc
ON CHARACTERISTICS*					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.0 mA)		$V_{GS(th)}$	2.0	4.0	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 2.25 Adc)	T_A = 25°C T_A = 125°C	$r_{DS(on)}$	— —	0.8 1.5	Ohm
Drain-Source On-Voltage (V_{GS} = 10 V, I_D = 3.5 Adc)		$V_{DS(on)}$	—	2.8	Vdc
Forward Transconductance (V_{DS} = 5.0 V, I_D = 2.25 Adc)		g_{fs}	1.5	4.5	mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	200	600	pF
Output Capacitance		C_{oss}	60	300	
Reverse Transfer Capacitance		C_{rss}	15	80	
SWITCHING CHARACTERISTICS*					
Turn-On Delay Time	(V_{DD} = 74 V, I_D = 2.25 A, R_{gen} = 50 ohms)	$t_{d(on)}$	—	40	ns
Rise Time		t_r	—	50	
Turn-Off Delay Time		$t_{d(off)}$	—	50	
Fall Time		t_f	—	50	
SOURCE-DRAIN DIODE CHARACTERISTICS*					
Forward Diode Voltage	(I_S = Rated $I_{D(on)}$, V_{GS} = 0)	V_{SD}	0.7	1.5	Vdc
Forward Turn-On Time		t_{on}	—	Negligible	ns
Reverse Recovery Time		t_{rr}	—	350	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

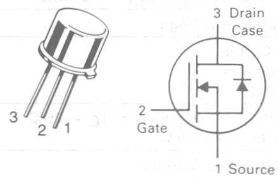
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	100	Vdc
Drain-Gate Voltage (R_{GS} = 1.0 mΩ)	V_{DGR}	100	Vdc
Gate-Source Voltage	V_{GS}	±20	Vdc
Drain Current Continuous Pulsed	 I_D I_{DM}	 8.0 32	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	25 0.2	Watts W/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Case	$R_{\theta JC}$	5.0	°C/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	175	°C/W
Maximum Lead Temperature 1.6 mm from Case for 10 s	T_L	300	°C

CASE 79-03, STYLE 6
TO-39 (TO-205AF)



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 0.25 mA)	$V_{(BR)DSS}$	100	—	Vdc
Zero Gate Voltage Drain Current (V_{DS} = Rated V_{DSS}, V_{GS} = 0) (V_{DS} = 80 V, V_{GS} = 0, T_J = 125°C)	I_{DSS}	 — —	 250 1000	μAdc
Gate-Body Leakage Current, Forward (V_{GS} = 20 Vdc, V_{DS} = 0)	I_{GSSF}	—	100	nAdc
Gate-Body Leakage Current, Reverse (V_{GS} = −20 Vdc, V_{DS} = 0)	I_{GSSR}	—	−100	nAdc
ON CHARACTERISTICS*				
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 0.5 mA)	$V_{GS(th)}$	2.0	4.0	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 5.0 Adc) T_A = 125°C	$r_{DS(on)}$	— —	0.18 0.35	Ohm
Drain-Source On-Voltage (V_{GS} = 10 V, I_D = 8.0 Adc)	$V_{DS(on)}$	—	1.56	Vdc
Forward Transconductance (V_{DS} = 15 V, I_D = 5.0 Adc)	g_{fs}	3.0	9.0	mhos
DYNAMIC CHARACTERISTICS				
Input Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	350	900	pF
Output Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{oss}	150	500	pF
Reverse Transfer Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{rss}	50	150	pF
SWITCHING CHARACTERISTICS*				
Turn-On Delay Time (V_{DD} = 30 V, I_D = 5.0 Adc, R_{gen} = 50 ohms)	$t_{d(on)}$	—	30	ns
Rise Time (V_{DD} = 30 V, I_D = 5.0 Adc, R_{gen} = 50 ohms)	t_r	—	75	ns
Turn-Off Delay Time (V_{DD} = 30 V, I_D = 5.0 Adc, R_{gen} = 50 ohms)	$t_{d(off)}$	—	40	ns
Fall Time (V_{DD} = 30 V, I_D = 5.0 Adc, R_{gen} = 50 ohms)	t_f	—	45	ns
SOURCE-DRAIN DIODE CHARACTERISTICS*				
Diode Forward Voltage (I_S = Rated $I_{D(on)}$, V_{GS} = 0)	V_{SD}	0.75	1.5	Vdc
Forward Turn-On Time (I_S = Rated $I_{D(on)}$, V_{GS} = 0)	t_{on}	—	Negligible	ns
Reverse Recovery Time (I_S = Rated $I_{D(on)}$, V_{GS} = 0)	t_{rr}	—	300	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

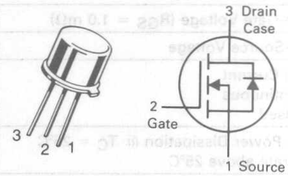
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	200	Vdc
Drain-Gate Voltage (R_{GS} = 1.0 mΩ)	V_{DGR}	200	Vdc
Gate-Source Voltage	V_{GS}	±20	Vdc
Drain Current Continuous Pulsed	I_D I_{DM}	 5.5 22	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	25 0.2	Watts W/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Case	$R_{\theta JC}$	5.0	°C/W
Maximum Lead Temperature 1.6 mm from Case for 10 s	T_L	300	°C

CASE 79-03, STYLE 6
TO-39 (TO-205AF)



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

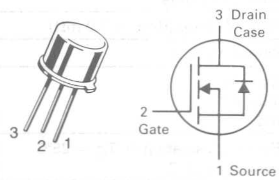
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 0.25 mA)		$V_{(BR)DSS}$	200	—	Vdc
Zero Gate Voltage Drain Current (V_{DS} = Rated V_{DSS}, V_{GS} = 0) (V_{DS} = 0.8 Rated V_{DSS}, V_{GS} = 0, T_J = 125°C)		I_{DSS}	 — —	 250 1000	μAdc
Gate-Body Leakage Current, Forward (V_{GS} = 20 Vdc, V_{DS} = 0)		I_{GSSF}	—	100	nAdc
Gate-Body Leakage Current, Reverse (V_{GS} = −20 Vdc, V_{DS} = 0)		I_{GSSR}	—	100	nAdc
ON CHARACTERISTICS*					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 0.5 mA)		$V_{GS(th)}$	2.0	4.0	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 3.5 Adc)	T_A = 25°C T_A = 125°C	$r_{DS(on)}$		0.4 0.75	Ohm
Drain-Source On-Voltage (V_{GS} = 10 V, I_D = 5.5 Adc)		$V_{DS(on)}$	—	2.2	Vdc
Forward Transconductance (V_{DS} = 5.0 V, I_D = 3.5 Adc)		g_{fs}	2.5	7.5	mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	350	900	pF
Output Capacitance		C_{oss}	100	450	
Reverse Transfer Capacitance		C_{rss}	40	150	
SWITCHING CHARACTERISTICS*					
Turn-On Delay Time	(V_{DD} ≃ 77 V, I_D = 3.5 A, R_{gen} = 50 ohms)	$t_{d(on)}$	—	30	ns
Rise Time		t_r	—	50	
Turn-Off Delay Time		$t_{d(off)}$	—	50	
Fall Time		t_f	—	40	
SOURCE-DRAIN DIODE CHARACTERISTICS*					
	(I_S = Rated $I_{D(on)}$, V_{GS} = 0)	V_{SD}	0.7	1.4	Vdc
Forward Turn-On Time		t_{on}	—	Negligible	ns
Reverse Recovery Time		t_{rr}	450 (Typ)	—	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

6

2N6800

CASE 79-03, STYLE 6
TO-39 (TO-205AF)



TMOS FET
TRANSISTOR

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	400	Vdc
Drain-Gate Voltage (R_{GS} = 1.0 mΩ)	V_{DGR}	400	Vdc
Gate-Source Voltage	V_{GS}	±20	Vdc
Drain Current Continuous Pulsed	 I_D I_{DM}	 3.0 14	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	25 20	Watts W/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Case	$R_{\theta JC}$	5.0	°C/W
Maximum Lead Temperature 1.6 mm from Case for 10 s	T_L	300	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

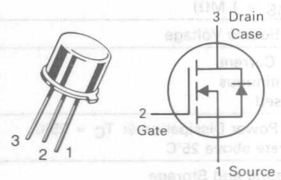
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 0.25 mA)		$V_{(BR)DSS}$	400	—	Vdc
Zero Gate Voltage Drain Current (V_{DS} = Rated V_{DSS}, V_{GS} = 0) (V_{DS} = 0.8 Rated V_{DSS}, V_{GS} = 0, T_J = 125°C)		I_{DSS}	 — —	 250 1000	μAdc
Gate-Body Leakage Current, Forward (V_{GS} = 20 Vdc, V_{DS} = 0)		I_{GSSF}	—	100	nAdc
Gate-Body Leakage Current, Reverse (V_{GS} = −20 Vdc, V_{DS} = 0)		I_{GSSR}	—	−100	nAdc
ON CHARACTERISTICS*					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 0.5 mA)		$V_{GS(th)}$	2.0	4.0	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 2.0 Adc)	 T_A = 125°C	$r_{DS(on)}$	— —	1.0 2.4	Ohm
Drain-Source On-Voltage (V_{GS} = 10 V, I_D = 3.0 Adc)		$V_{DS(on)}$	—	3.0	Vdc
Forward Transconductance (V_{DS} = 5.0 V, I_D = 2.0 Adc)		g_{fs}	2.0	6.0	mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	350	900	pF
Output Capacitance		C_{oss}	50	300	
Reverse Transfer Capacitance		C_{rss}	20	80	
SWITCHING CHARACTERISTICS*					
Turn-On Delay Time	(V_{DD} = 176 V, I_D = 2.0 A, R_{gen} = 50 ohms)	$t_{d(on)}$	—	30	ns
Rise Time		t_r	—	35	
Turn-Off Delay Time		$t_{d(off)}$	—	55	
Fall Time		t_f	—	35	
SOURCE-DRAIN DIODE CHARACTERISTICS*					
	(I_S = Rated $I_{D(on)}$, V_{GS} = 0)	V_{SD}	0.7	1.4	Vdc
Forward Turn-On Time		t_{on}	—	Negligible	ns
Reverse Recovery Time		t_{rr}	—	600	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

6

2N6802

CASE 79-03, STYLE 6
TO-39 (TO-205AF)



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	500	Vdc
Drain-Gate Voltage (R_{GS} = 1.0 mΩ)	V_{DGR}	500	Vdc
Gate-Source Voltage	V_{GS}	±20	Vdc
Drain Current Continuous Pulsed	 I_D I_{DM}	 3.5 11	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	25 0.2	Watts W/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Case	$R_{\theta JC}$	5.0	°C/W
Maximum Lead Temperature 1.6 mm from Case for 10 s	T_L	300	°C

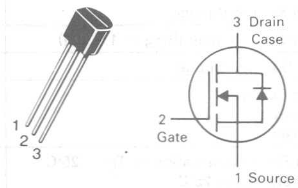
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 0.25 mA)	$V_{(BR)DSS}$	500	—	Vdc
Zero-Gate Voltage Drain Current (V_{DS} = Rated V_{DSS}, V_{GS} = 0) (V_{DS} = 0.8 Rated V_{DSS}, V_{GS} = 0, T_J = 125°C)	I_{DSS}	 — —	 250 1000	μAdc
Gate-Body Leakage Current, Forward (V_{GS} = 20 Vdc, V_{DS} = 0)	I_{GSSF}	—	100	nAdc
Gate-Body Leakage Current, Reverse (V_{GS} = −20 Vdc, V_{DS} = 0)	I_{GSSR}	—	−100	nAdc
ON CHARACTERISTICS*				
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 0.5 mA)	$V_{GS(th)}$	2.0	4.0	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 1.5 Adc) T_A = 125°C	$r_{DS(on)}$	— —	1.5 3.5	Ohms
Drain-Source On-Voltage (V_{GS} = 10 V, I_D = 2.5 Adc)	$V_{DS(on)}$	—	3.75	Vdc
Forward Transconductance (V_{DS} = 5.0 V, I_D = 1.5 Adc)	g_{fs}	1.5	4.5	mhos
DYNAMIC CHARACTERISTICS				
Input Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	350	900	pF
Output Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{oss}	25	200	pF
Reverse Transfer Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{rss}	15	60	pF
SWITCHING CHARACTERISTICS*				
Turn-On Delay Time (V_{DD} ≈ 225 V, I_D = 1.5 V, R_{gen} = 50 ohms)	$t_{d(on)}$	—	30	ns
Rise Time (V_{DD} ≈ 225 V, I_D = 1.5 V, R_{gen} = 50 ohms)	t_r	—	30	ns
Turn-Off Delay Time (V_{DD} ≈ 225 V, I_D = 1.5 V, R_{gen} = 50 ohms)	$t_{d(off)}$	—	55	ns
Fall Time (V_{DD} ≈ 225 V, I_D = 1.5 V, R_{gen} = 50 ohms)	t_f	—	30	ns
SOURCE-DRAIN DIODE CHARACTERISTICS*				
(I_S = Rated I_D, V_{GS} = 0)	V_{SD}	0.7	1.4	Vdc
Forward Turn-On Time (I_S = Rated I_D, V_{GS} = 0)	t_{on}	—	Negligible	ns
Reverse Recovery Time (I_S = Rated I_D, V_{GS} = 0)	t_{rr}	800		ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2N7000

CASE 29-04, STYLE 7
TO-92 (TO-226AA)



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	Vdc
Drain-Gate Voltage (R_{GS} = 1 MΩ)	V_{DGR}	60	Vdc
Gate-Source Voltage	V_{GS}	±40	Vdc
Drain Current			mAdc
Continuous	I_D	200	
Pulsed	I_{DM}	500	
Total Power Dissipation @ T_C = 25°C	P_D	400	mW
Derate above 25°C		3.2	mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	312.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/16″ from case for 10 seconds	T_L	300	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 10 μA)	$V_{(BR)DSS}$	60	—	Vdc
Zero Gate Voltage Drain Current	I_{DSS}			
(V_{DS} = 48 V, V_{GS} = 0)		—	1.0	μAdc
(V_{DS} = 48 V, V_{GS} = 0, T_J = 125°C)		—	1.0	mA
Gate-Body Leakage Current, Forward (V_{GSF} = 15 Vdc, V_{DS} = 0)	I_{GSSF}	—	−10	nAdc
ON CHARACTERISTICS*				
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.0 mA)	$V_{GS(th)}$	0.8	3.0	Vdc
Static Drain-Source On-Resistance	$r_{DS(on)}$			Ohm
(V_{GS} = 10 Vdc, I_D = 0.5 Adc)		—	5.0	
(V_{GS} = 10 Vdc, I_D = 0.5 V, T_C = 125°C)		—	9.0	
Drain-Source On-Voltage	$V_{DS(on)}$			Vdc
(V_{GS} = 10 V, I_D = 0.5 Adc)		—	2.5	
(V_{GS} = 4.5 V, I_D = 75 mA)		—	0.4	
On-State Drain Current (V_{GS} = 4.5 V, V_{DS} = 10 V)	$I_{d(on)}$	75	—	mA
Forward Transconductance (V_{DS} = 10 V, I_D = 200 mA)	g_{fs}	100	—	μmhos
DYNAMIC CHARACTERISTICS				
Input Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	60	pF
Output Capacitance	C_{oss}	—	25	
Reverse Transfer Capacitance	C_{rss}	—	5.0	
SWITCHING CHARACTERISTICS*				
Turn-On Delay Time (V_{DD} = 15 V, I_D = 600 mA, R_{gen} = 25 ohms, R_L = 25 ohms)	t_{on}	—	10	ns
Turn-Off Delay Time	t_{off}	—	10	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

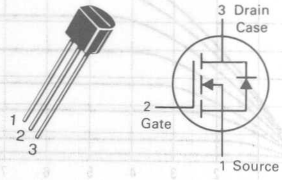
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	Vdc
Drain-Gate Voltage (R_{GS} = 1 MΩ)	V_{DGR}	60	Vdc
Gate-Source Voltage	V_{GS}	±40	Vdc
Drain Current Continuous Pulsed	 I_D I_{DM}	 150 1000	mAdc
Total Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	400 3.2	mW mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Ambient	$R_{\theta JA}$	312.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/16″ from case for 10 seconds	T_L	300	°C

CASE 29-04, STYLE 22
TO-92 (TO-226AA)



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 100 μA)	$V_{(BR)DSS}$	60	—	Vdc
Zero Gate Voltage Drain Current (V_{DS} = 50 V, V_{GS} = 0) (V_{DS} = 50 V, V_{GS} = 0, T_J = 125°C)	I_{DSS}	 — —	 1.0 500	μAdc
Gate-Body Leakage Current, Forward (V_{GSF} = 30 Vdc, V_{DS} = 0)	I_{GSSF}	—	−100	nAdc
ON CHARACTERISTICS*				
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μA)	$V_{GS(th)}$	1.0	2.5	Vdc
Static Drain-Source On-Resistance (V_{GS} = 5.0 Vdc, I_D = 50 Adc) (V_{GS} = 10 Vdc, I_D = 500 mAdc, T_C = 125°C)	$r_{DS(on)}$	 — —	 7.5 13.5	Ohm
Drain-Source On-Voltage (V_{GS} = 5.0 V, I_D = 50 mA) (V_{GS} = 10 V, I_D = 500 mA)	$V_{DS(on)}$	 — —	 1.5 3.75	Vdc
On-State Drain Current (V_{GS} = 10 V, $V_{DS} \geq$ 2.0 $V_{D(on)}$)	$I_{D(on)}$	500	—	mA
Forward Transconductance ($V_{DS} \geq$ 2.0 $V_{DS(on)}$, I_D = 200 mA)	g_{fs}	80	—	μmhos
DYNAMIC CHARACTERISTICS				
Input Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	50	pF
Output Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{oss}	—	25	pF
Reverse Transfer Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{rss}	—	5.0	pF
SWITCHING CHARACTERISTICS*				
Turn-On Delay Time (V_{DD} = 30 V, I_D = 200 mA, R_{gen} = 25 ohms, R_L = 150 ohms)	t_{on}	—	20	ns
Turn-Off Delay Time (V_{DD} = 30 V, I_D = 200 mA, R_{gen} = 25 ohms, R_L = 150 ohms)	t_{off}	—	20	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

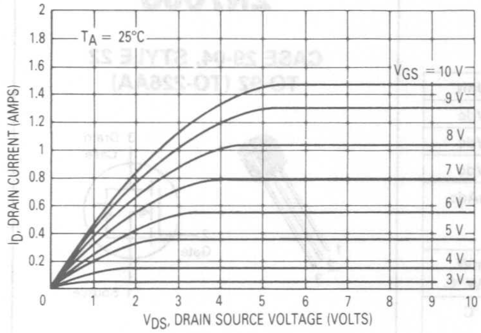


Figure 1. Ohmic Region

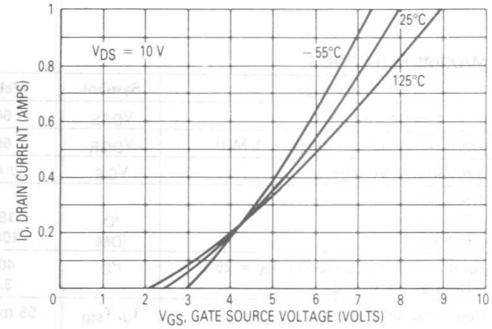


Figure 2. Transfer Characteristics

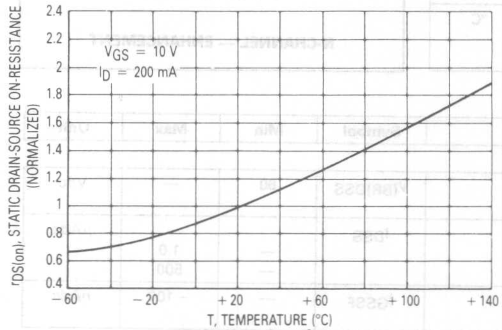


Figure 3. Temperature versus Static Drain-Source On-Resistance

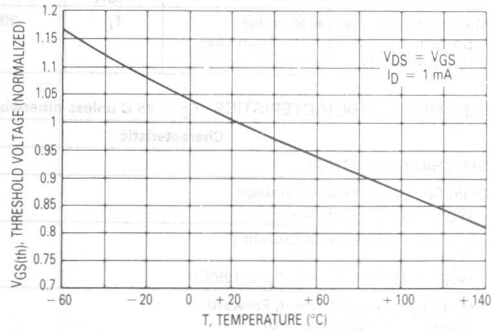
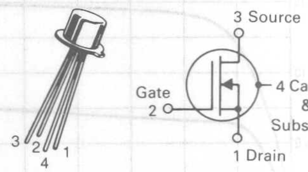


Figure 4. Temperature versus Gate Threshold Voltage

6

3N128

CASE 20-03, STYLE 7
TO-72 (TO-206AF)



MOSFET AMPLIFIER

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	+20	Vdc
Drain-Gate Voltage	V_{DG}	+20	Vdc
Gate-Source Voltage	V_{GS}	±10	Vdc
Drain Current	I_D	50	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	330 2.2	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +175	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage(1) (I_G = −10 μAdc, V_{DS} = 0)	$V_{(BR)DSS}$	−50	—	Vdc
Gate Reverse Current (V_{GS} = −8.0 Vdc, V_{DS} = 0) (V_{GS} = −8.0 Vdc, V_{DS} = 0, T_A = 125°C)	I_{GSS}	 — —	 0.05 5.0	nAdc
Gate Source Cutoff Voltage (V_{DS} = 15 Vdc, I_D = 50 μAdc)	$V_{GS(off)}$	−0.5	−8.0	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current(2) (V_{DS} = 15 Vdc, V_{GS} = 0)	I_{DSS}	5.0	25	mAdc
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance (V_{DS} = 15 Vdc, I_D = 5.0 mAdc, f = 1.0 kHz)	$\|Y_{fs}\|$	5000	12,000	μmhos
Input Admittance (V_{DS} = 15 Vdc, I_D = 5.0 mAdc, f = 200 MHz)	$Re(y_{is})$	—	800	μmhos
Output Conductance (V_{DS} = 15 Vdc, I_D = 5.0 mAdc, f = 200 MHz)	$Re(y_{os})$	—	500	μmhos
Forward Transconductance (V_{DS} = 15 Vdc, I_D = 5.0 mAdc, f = 200 MHz)	$Re(y_{fs})$	5000	—	μmhos
Input Capacitance (V_{DS} = 15 Vdc, I_D = 5.0 mAdc, f = 1.0 MHz)	C_{iss}	—	7.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, I_D = 5.0 mAdc, f = 1.0 MHz)	C_{rss}	0.05	0.35	pF
FUNCTIONAL CHARACTERISTICS				
Noise Figure (V_{DS} = 15 Vdc, I_D = 5.0 mAdc, f = 200 MHz)	NF	—	5.0	dB
Power Gain (V_{DS} = 15 Vdc, I_D = 5.0 mAdc, f = 200 MHz)	P_G	13.5	23	dB

(1) Caution Destructive Test, can damage gate oxide beyond operation.
(2) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

FIGURE 1 – DRAIN CHARACTERISTICS

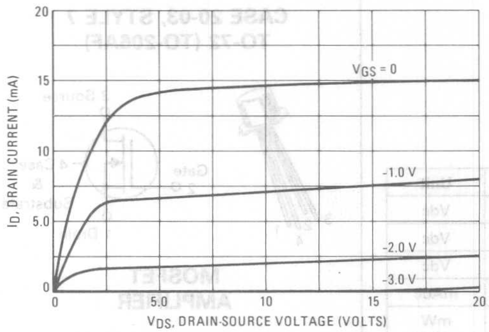
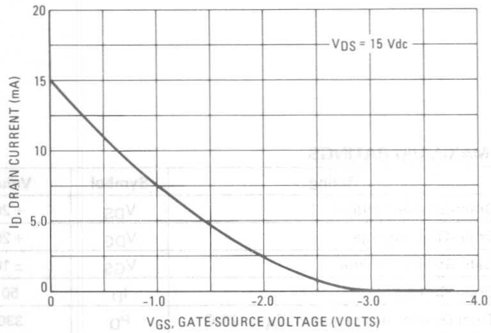


FIGURE 2 – TRANSFER CHARACTERISTICS



TYPICAL 1 kHz DRAIN CHARACTERISTICS

(T_A = 25°C, V_{DS} = 15 Vdc, f = 1.0 kHz)

FIGURE 3 – FORWARD TRANSADMITTANCE versus GATE BIAS VOLTAGE

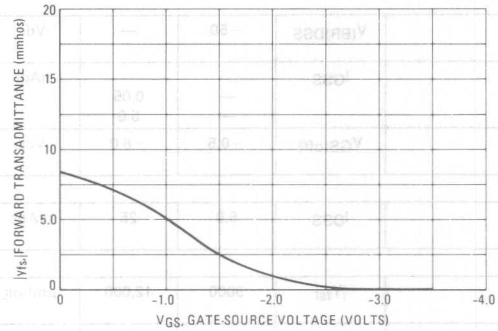
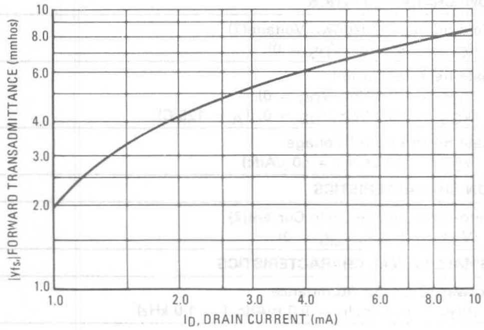


FIGURE 4 – FORWARD TRANSADMITTANCE versus DRAIN CURRENT



TYPICAL 200 MHz COMMON-SOURCE ADMITTANCE CHARACTERISTICS

(T_A = 25°C, V_{DS} = 15 Vdc, f = 200 MHz)

FIGURE 5 – INPUT ADMITTANCE (y_{is}) COMPONENTS

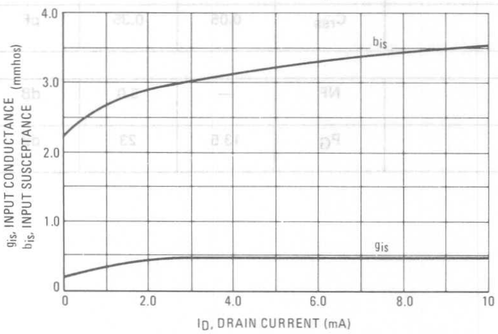
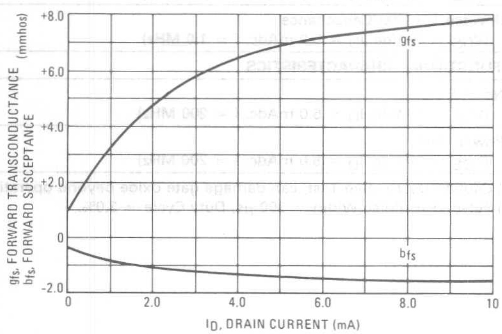
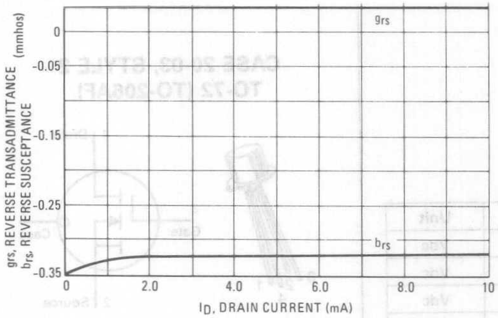


FIGURE 6 – FORWARD TRANSADMITTANCE (y_{fs}) COMPONENTS





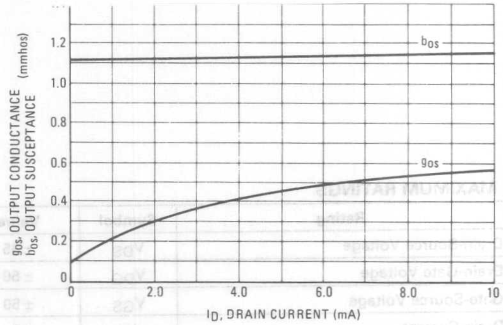


FIGURE 9 — POWER GAIN AND NOISE FIGURE versus DRAIN CURRENT

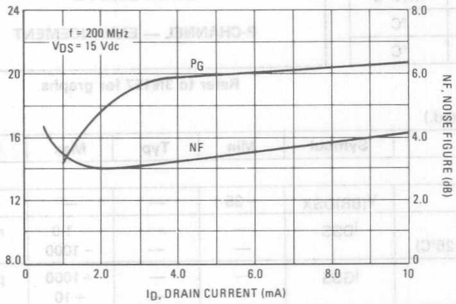


FIGURE 10 — POWER GAIN AND NOISE FIGURE versus DRAIN VOLTAGE

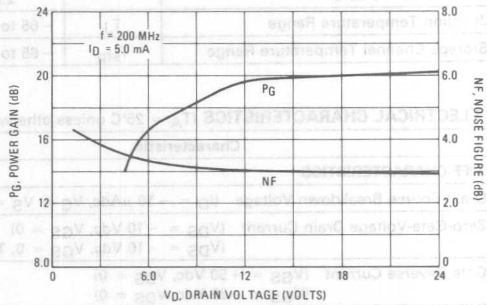


FIGURE 11 — THIRD ORDER INTERMODULATION DISTORTION

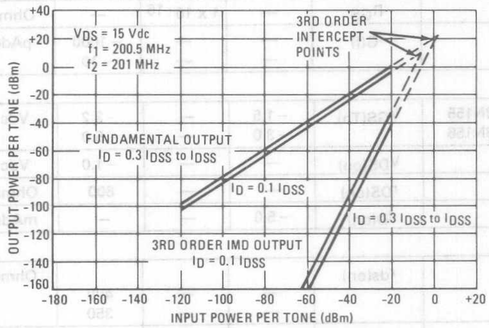
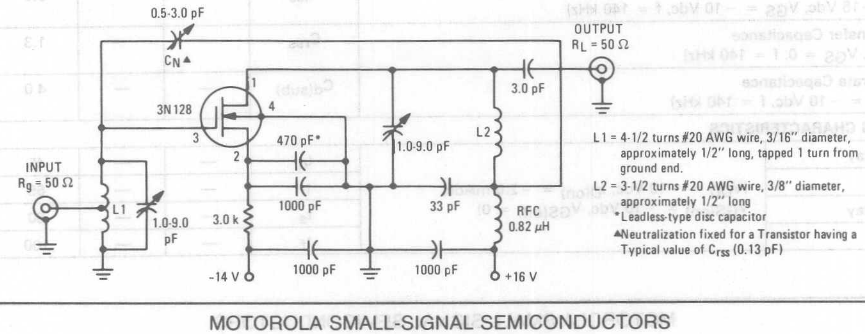


Figure 11 shows the typical third order intermodulation distortion (IMD) performance of the 3N128 at 200 MHz.

Both fundamental output and third order IMD output characteristics are plotted. The curves have been extrapolated to show the third order intermodulation output intercept point.

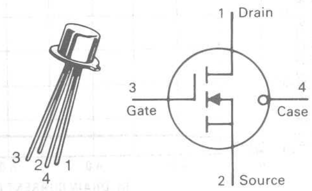
Performance for drain currents from I_{DSS} to $0.1\ I_{DSS}$, is given. The power gain and noise figure test amplifier shown in Figure 12 was used to generate the IMD data.

FIGURE 12 — POWER GAIN, NOISE FIGURE AND INTERMODULATION DISTORTION TEST CIRCUIT



3N155
3N156

CASE 20-03, STYLE 2
TO-72 (TO-206AF)



MOSFET
SWITCHING

P-CHANNEL — ENHANCEMENT

Refer to 3N157 for graphs.

MAXIMUM RATINGS

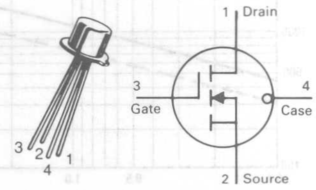
Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	±35	Vdc
Drain-Gate Voltage	V_{DG}	±50	Vdc
Gate-Source Voltage	V_{GS}	±50	Vdc
Drain Current	I_D	30	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 2.0	mW mW/°C
Junction Temperature Range	T_J	−65 to +175	°C
Storage Channel Temperature Range	T_{stg}	−65 to +175	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage (I_D = −10 μAdc, V_G = V_S = 0)		$V_{(BR)DSX}$	−35	—	—	Vdc
Zero-Gate-Voltage Drain Current (V_{DS} = −10 Vdc, V_{GS} = 0) (V_{DS} = −10 Vdc, V_{GS} = 0, T_A = 125°C)		I_{DSS}	— —	— —	−1.0 −1000	nAdc
Gate Reverse Current (V_{GS} = +50 Vdc, V_{DS} = 0) (V_{GS} = +25 Vdc, V_{DS} = 0)		I_{GSS}	— —	— —	+1000 +10	pAdc
Resistance Drain Source (I_D = 0, V_{GS} = 0)		$r_{DS(off)}$	$1 \times 10^{+10}$	—	—	Ohms
Resistance Gate Source Input (V_{GS} = −25 Vdc)		R_{GS}	—	$1 \times 10^{+16}$	—	Ohms
Gate Forward Leakage Current (V_{GS} = −50 Vdc, V_{DS} = 0) (V_{GS} = −25 Vdc, V_{DS} = 0)		$I_{G(f)}$	— —	— —	−1000 −10	pAdc
ON CHARACTERISTICS						
Gate Threshold Voltage (V_{DS} = −10 Vdc, I_D = −10 μAdc)	3N155 3N156	$V_{GS(Th)}$	−1.5 −3.0	— —	−3.2 −5.0	Vdc
Drain-Source On-Voltage (I_D = −2.0 mAdc, V_{GS} = −10 Vdc)		$V_{DS(on)}$	—	—	−1.0	Vdc
Static Drain-Source On Resistance (I_D = 0 mAdc, V_{GS} = −10 Vdc)		$r_{DS(on)}$	—	—	600	Ohms
On-State Drain Current (V_{DS} = −15 Vdc, V_{GS} = −10 Vdc)		$I_{D(on)}$	−5.0	—	—	mAdc
SMALL-SIGNAL CHARACTERISTICS						
Drain-Source Resistance (V_{GS} = −10 Vdc, I_D = 0, f = 1.0 kHz) (V_{GS} = −15 Vdc, I_D = 0, f = 1.0 kHz)		$r_{ds(on)}$	— —	— —	400 350	Ohms
Forward Transfer Admittance (V_{DS} = −15 Vdc, I_D = −2.0 mAdc, f = 1.0 kHz)		$\lvert y_{fs}\rvert$	1000	—	4000	μmhos
Input Capacitance (V_{DS} = −15 Vdc, V_{GS} = −10 Vdc, f = 140 kHz)		C_{iss}	—	—	5.0	pF
Reverse Transfer Capacitance (V_{DS} = 0, V_{GS} = 0, f = 140 kHz)		C_{rss}	—	—	1.3	pF
Drain-Substrate Capacitance ($V_{D(SUB)}$ = −10 Vdc, f = 140 kHz)		$C_{d(sub)}$	—	—	4.0	pF
SWITCHING CHARACTERISTICS						
Turn-On Delay	(V_{DD} = −10 Vdc, $I_{D(on)}$ = −2.0 mAdc, $V_{GS(on)}$ = −10 Vdc, $V_{GS(off)}$ = 0)	t_d	—	—	45	μs
Rise Time		t_r	—	—	65	ns
Turn-Off Delay		t_s	—	—	60	ns
Fall Time		t_f	—	—	100	ns

3N157
3N158

CASE 20-03, STYLE 2
TO-72 (TO-206AF)



MOSFET
AMPLIFIER AND SWITCHING

P-CHANNEL — ENHANCEMENT

6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage*	V_{DS}	±35	Vdc
Drain-Gate Voltage*	V_{DG}	±50	Vdc
Gate-Source Voltage*	V_{GS}	±50	Vdc
Drain Current*	I_D	30	mAdc
Total Device Dissipation @ T_A = 25°C* Derate above 25°C*	P_D	300 1.7	mW mW/°C
Junction Temperature Range*	T_J	−65 to +175	°C
Storage Channel Temperature Range*	T_{stg}	−65 to +175	°C

*JEDEC Registered Limits

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (I_D = −10 μAdc, V_G = V_S = 0)	$V_{(BR)DSX}$	−35	—	—	Vdc
Zero-Gate-Voltage Drain Current (V_{DS} = −15 Vdc, V_{GS} = 0) (V_{DS} = −35 Vdc, V_{GS} = 0)	I_{DSS}	— —	— —	−1.0 −10	nAdc μAdc
Gate Reverse Current* (V_{GS} = +25 Vdc, V_{DS} = 0) (V_{GS} = +50 Vdc, V_{DS} = 0)	I_{GSS}	— —	— —	+10 +10	pAdc nAdc
Input Resistance (V_{GS} = −25 Vdc)	R_{GS}	—	$1 \times 10^{+12}$	—	Ohms
Gate Source Voltage* (V_{DS} = −15 Vdc, I_D = −0.5 mAdc) 3N157 3N158	V_{GS}	 −1.5 −3.0	 — —	 −5.5 −7.0	Vdc
Gate Forward Current* (V_{GS} = −25 Vdc, V_{DS} = 0) (V_{GS} = −50 Vdc, V_{DS} = 0) (V_{GS} = −25 Vdc, V_{DS} = 0, T_A = +55°C) (V_{GS} = −50 Vdc, V_{DS} = 0, T_A = +55°C)	$I_{G(f)}$	— — — —	— — — —	−10 −1.0 −10 −1.0	pAdc nAdc nAdc μAdc
ON CHARACTERISTICS					
Gate Threshold Voltage* (V_{DS} = −15 Vdc, I_D = −10 μAdc) 3N157 3N158	$V_{GS(Th)}$	 −1.5 −3.0	 — —	 −3.2 −5.0	Vdc
On-State Drain Current* (V_{DS} = −15 Vdc, V_{GS} = −10 Vdc)	$I_{D(on)}$	−5.0	—	—	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance* (V_{DS} = −15 Vdc, I_D = −2.0 mAdc, f = 1.0 kHz)	$\lvert y_{fs} \rvert$	1000	—	4000	μmhos
Output Admittance* (V_{DS} = −15 Vdc, I_D = −2.0 mAdc, f = 1.0 kHz)	$\lvert y_{os} \rvert$	—	—	60	μmhos
Input Capacitance* (V_{DS} = −15 Vdc, V_{GS} = 0, f = 140 kHz)	C_{iss}	—	—	5.0	pF
Reverse Transfer Capacitance* (V_{DS} = −15 Vdc, V_{GS} = 0, f = 140 kHz)	C_{rss}	—	—	1.3	pF
Drain-Substrate Capacitance ($V_{D(SUB)}$ = −10 Vdc, f = 140 kHz)	$C_{d(sub)}$	—	—	4.0	pF
Noise Voltage (R_S = 0, BW = 1.0 Hz, V_{DS} = −15 Vdc, I_D = −2.0 mAdc, f = 100 Hz) (R_S = 0, BW = 1.0 Hz, V_{DS} = −15 Vdc, I_D = −2.0 mAdc, f = 1.0 kHz)	e_n	 — —	 300 120	 — 500	$NV/\sqrt{Hz}$

*JEDEC Registered Limits

FIGURE 1 – FORWARD TRANSCONDUCTANCE

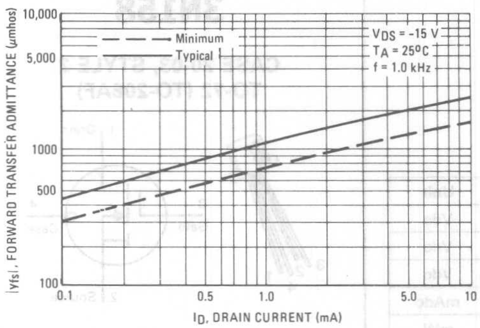


FIGURE 2 – OUTPUT TRANSCONDUCTANCE

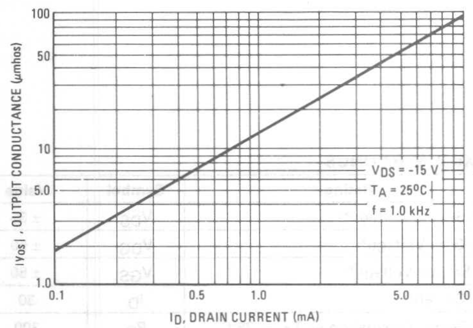


FIGURE 3 – FORWARD TRANSCONDUCTANCE versus TEMPERATURE

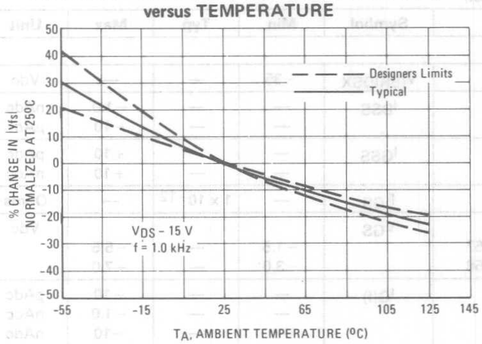


FIGURE 4 – BIAS CURVE

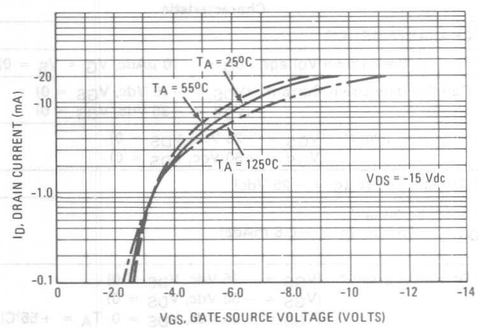


FIGURE 5 – "ON" DRAIN-SOURCE VOLTAGE

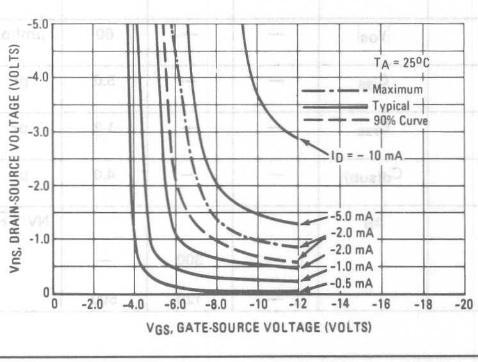


FIGURE 6 – EQUIVALENT INPUT NOISE VOLTAGE

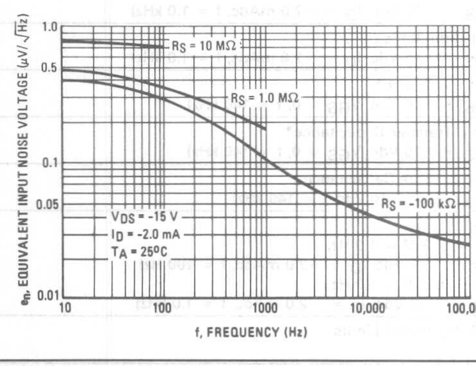


FIGURE 7 — TURN-ON DELAY TIME

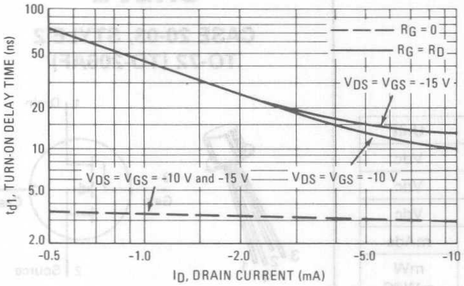


FIGURE 8 — RISE TIME

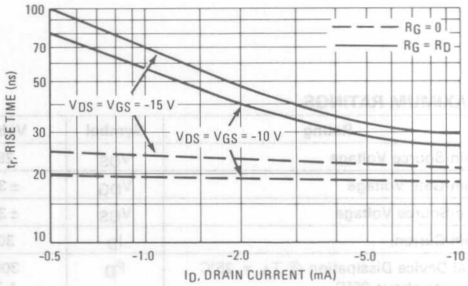


FIGURE 9 — TURN-OFF DELAY TIME

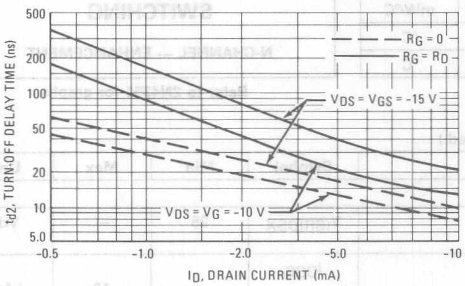


FIGURE 10 — FALL TIME

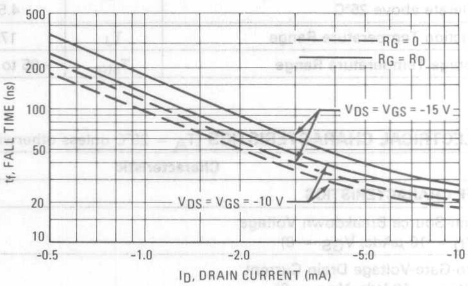


FIGURE 11 — SWITCHING CIRCUIT and WAVEFORMS

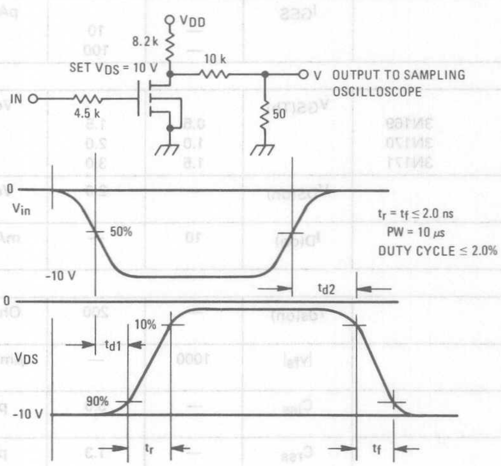
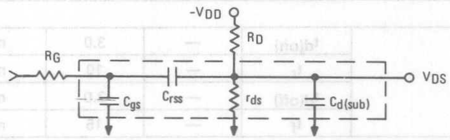


FIGURE 12 — SWITCHING CIRCUIT with MOSFET EQUIVALENT MODEL



The switching characteristics shown above were measured in a test circuit similar to Figure 11. At the beginning of the switching interval, the gate voltage is at ground and the gate source capacitance ($C_{gs} \cdot C_{rss} \cdot C_{rss}$) has no charge. The drain voltage is at V_{DD} and thus the feedback capacitance (C_{rss}) is charged to V_{DD}. Similarly, the drain substrate capacitance ($C_{d(sub)}$) is charged to V_{DD} since the substrate and source are connected to ground.

During the turn-on interval C_{gs} is charged to V_{GS} (the input voltage) through R_G (generator impedance) (Figure 12). C_{rss} must be discharged to $V_{GS} \cdot V_{D(on)}$ through R_G and the parallel combination of the load resistor (R_D) and the channel resistance (r_{ds}). In addition, $C_{d(sub)}$ is discharged to a low value ($V_{D(on)}$) through R_D in parallel with r_{ds}. During turn-off this charge flow is reversed.

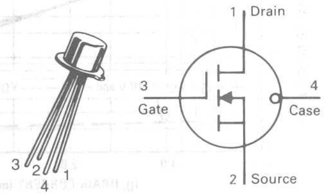
Predicting turn-on time proves to be somewhat difficult since the channel resistance (r_{ds}) is a function of the gate source voltage (V_{GS}). As C_{gs} becomes charged V_{GS} is approaching V_{in} and r_{ds} decreases (see Figure 5) and since C_{rss} and $C_{d(sub)}$ are charged through r_{ds}, turn-on time is quite non-linear.

If the charging time of C_{gs} is short compared to that of C_{rss} and $C_{d(sub)}$, then r_{ds} (which is in parallel with R_D) will be low compared to R_D during the switching interval and will largely determine the turn-on time. On the other hand, during turn-off r_{ds} will be almost an open circuit requiring C_{rss} and $C_{d(sub)}$ to be charged through R_D and resulting in a turn-off time that is long compared to the turn-on time. This is especially noticeable for the curves where $R_G \cdot 0$ and C_{gs} is charged through the pulse generator impedance only.

The switching curves shown with $R_G \cdot R_D$ simulate the switching behavior of cascaded stages where the driving source impedance is normally the same as the load impedance. The set of curves with $R_G \cdot 0$ simulates a low source impedance drive such as might occur in complementary logic circuits.

3N169
3N170
3N171

CASE 20-03, STYLE 2
TO-72 (TO-206AF)



MOSFET SWITCHING

N-CHANNEL — ENHANCEMENT

Refer to 2N4351 for graphs.

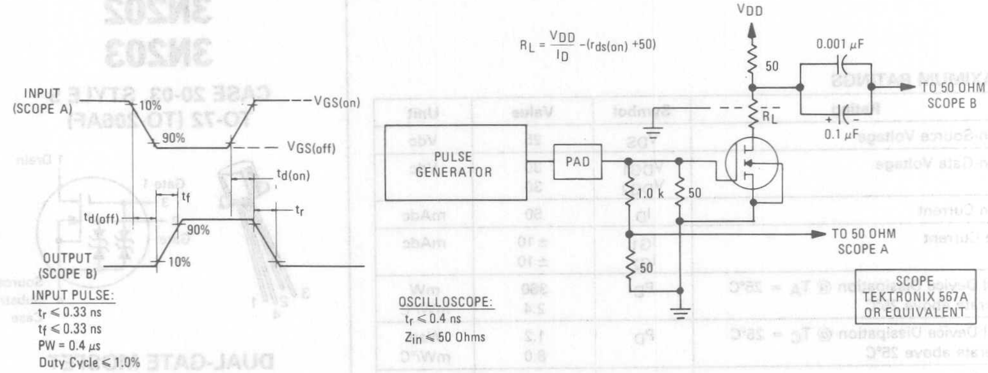
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG}	±35	Vdc
Gate-Source Voltage	V_{GS}	±35	Vdc
Drain Current	I_D	30	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	300 1.7	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	800 4.56	mW mW/°C
Junction Temperature Range	T_J	175	°C
Storage Temperature Range	T_{stg}	−65 to +175	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (I_D = 10 μAdc, V_{GS} = 0)		$V_{(BR)DSX}$	25	—	Vdc
Zero-Gate-Voltage Drain Current (V_{DS} = 10 Vdc, V_{GS} = 0) (V_{DS} = 10 Vdc, V_{GS} = 0, T_A = 125°C)		I_{DSS}	— 	10 1.0	nAdc μAdc
Gate Reverse Current (V_{GS} = −35 Vdc, V_{DS} = 0) (V_{GS} = −35 Vdc, V_{DS} = 0, T_A = 125°C)		I_{GSS}	— —	10 100	pAdc
ON CHARACTERISTICS					
Gate Threshold Voltage (V_{DS} = 10 Vdc, I_D = 10 μAdc)	3N169 3N170 3N171	$V_{GS(Th)}$	0.5 1.0 1.5	1.5 2.0 3.0	Vdc
Drain-Source On-Voltage (I_D = 10 mAdc, V_{GS} = 10 Vdc)		$V_{DS(on)}$	—	2.0	Vdc
On-State Drain Current (V_{GS} = 10 Vdc, V_{DS} = 10 Vdc)		$I_{D(on)}$	10	—	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Drain-Source Resistance (V_{GS} = 10 Vdc, I_D = 0, f = 1.0 kHz)		$r_{ds(on)}$	—	200	Ohms
Forward Transfer Admittance (V_{DS} = 10 Vdc, I_D = 2.0 mAdc, f = 1.0 kHz)		$\|y_{fs}\|$	1000	—	μmhos
Input Capacitance (V_{DS} = 10 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	5.0	pF
Reverse Transfer Capacitance (V_{DS} = 0, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	—	1.3	pF
Drain-Substrate Capacitance ($V_{D(SUB)}$ = 10 Vdc, f = 1.0 MHz)		$C_{d(sub)}$	—	5.0	pF
SWITCHING CHARACTERISTICS					
Turn-On Delay Time	(V_{DD} = 10 Vdc, $I_{D(on)}$ = 10 mAdc, $V_{GS(on)}$ = 10 Vdc, $V_{GS(off)}$ = 0, R_G' = 50 Ohms) See Figure 1	$t_{d(on)}$	—	3.0	ns
Rise Time		t_r	—	10	ns
Turn-Off Delay Time		$t_{d(off)}$	—	3.0	ns
Fall Time		t_f	—	15	ns

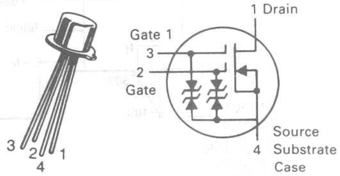
FIGURE 1 — SWITCHING TIME TEST CIRCUIT



6

3N203

CASE 20-03, STYLE 9
TO-72 (TO-206AF)



DUAL-GATE MOSFET VHF AMPLIFIER

N-CHANNEL — DEPLETION

Refer to MPF201 for additional graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG1} V_{DG2}	30 30	Vdc
Drain Current	I_D	50	mAdc
Gate Current	I_{G1} I_{G2}	±10 ±10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	360 2.4	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.2 8.0	Watt mW/°C
Lead Temperature	T_L	300	°C
Junction Temperature Range	T_J	−65 to +175	°C
Storage Channel Temperature Range	T_{stg}	−65 to +175	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage (I_D = 10 μAdc, V_S = 0, V_{G1S} = V_{G2S} = −5.0 Vdc)		$V_{(BR)DSX}$	25	—	—	Vdc
Gate 1-Source Breakdown Voltage(1) (I_{G1} = ±10 mAdc, V_{G2S} = V_{DS} = 0)		$V_{(BR)G1SO}$	±6.0	±12	±30	Vdc
Gate 2-Source Breakdown Voltage(1) (I_{G2} = ±10 mAdc, V_{G1S} = V_{DS} = 0)		$V_{(BR)G2SO}$	±6.0	±12	±30	Vdc
Gate 1 Leakage Current (V_{G1S} = ±5.0 Vdc, V_{G2S} = V_{DS} = 0) (V_{G1S} = −5.0 Vdc, V_{G2S} = V_{DS} = 0, T_A = 150°C)		I_{G1SS}	— —	±.040 —	±10 −10	nAdc μAdc
Gate 2 Leakage Current (V_{G2S} = ±5.0 Vdc, V_{G1S} = V_{DS} = 0) (V_{G2S} = −5.0 Vdc, V_{G1S} = V_{DS} = 0, T_A = 150°C)		I_{G2SS}	— —	±.050 —	±10 −10	nAdc μAdc
Gate 1 to Source Cutoff Voltage (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 20 μAdc)		$V_{G1S(off)}$	−0.5	−1.5	−5.0	Vdc
Gate 2 to Source Cutoff Voltage (V_{DS} = 15 Vdc, V_{G1S} = 0, I_D = 20 μAdc)		$V_{G2S(off)}$	−0.2	−1.4	−5.0	Vdc
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current(2) (V_{DS} = 15 Vdc, V_{G1S} = 0, V_{G2S} = 4.0 Vdc)	3N201,3N202 3N203	I_{DSS}	6.0 3.0	13 11	30 15	mAdc
SMALL-SIGNAL CHARACTERISTICS						
Forward Transfer Admittance(3) (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, V_{G1S} = 0, f = 1.0 kHz)	3N201,3N202 3N203	$\|Y_{fs}\|$	8.0 7.0	12.8 12.5	20 15	mmhos
Input Capacitance (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = I_{DSS}, f = 1.0 MHz)		C_{iss}	—	3.3	—	pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 10 mAdc, f = 1.0 MHz)		C_{rss}	0.005	0.014	0.03	pF
Output Capacitance (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = I_{DSS}, f = 1.0 MHz)		C_{oss}	—	1.7	—	pF
FUNCTIONAL CHARACTERISTICS						
Noise Figure (V_{DD} = 18 Vdc, V_{GG} = 7.0 Vdc, f = 200 MHz) (Figure 1) (V_{DD} = 18 Vdc, V_{GG} = 6.0 Vdc, f = 45 MHz) (Figure 3)	3N201 3N203	NF	— —	1.8 5.3	4.5 6.0	dB

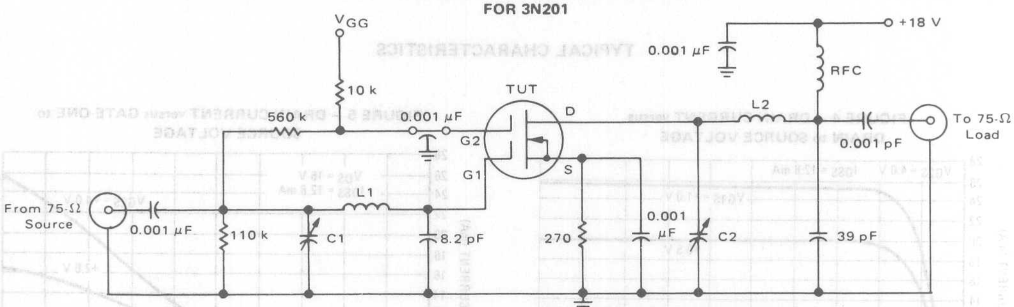
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
Common Source Power Gain		G_{ps}				dB
(V_{DD} = 18 Vdc, V_{GG} = 7.0 Vdc, f = 200 MHz) (Figure 1)	3N201		15	20	25	
(V_{DD} = 18 Vdc, V_{GG} = 6.0 Vdc, f = 45 MHz) (Figure 3)	3N203		20	25	30	
(V_{DD} = 18 Vdc, f_{LO} = 245 MHz, f_{RF} = 200 MHz) (Figure 2)	3N202	G_c(5)	15	19	25	
Bandwidth		BW				MHz
(V_{DD} = 18 Vdc, V_{GG} = 7.0 Vdc, f = 200 MHz) (Figure 1)	3N201		5.0	—	9.0	
(V_{DD} = 18 Vdc, f_{LO} = 245 MHz, f_{RF} = 200 MHz) (Figure 2)	3N202		4.5	—	7.5	
(V_{DD} = 18 Vdc, V_{GG} = 6.0 Vdc, f = 45 MHz) (Figure 3)	3N203		3.0	—	6.0	
Gain Control Gate-Supply Voltage(4)		$V_{GG(GC)}$				Vdc
(V_{DD} = 18 Vdc, ΔG_{ps} = −30 dB, f = 200 MHz) (Figure 1)	3N201		0	−1.0	−3.0	
(V_{DD} = 18 Vdc, ΔG_{ps} = −30 dB, f = 45 MHz) (Figure 3)	3N203		0	−0.6	−3.0	

(1) All gate breakdown voltages are measured while the device is conducting rated gate current. This ensures that the gate-voltage limiting network is functioning properly.
(2) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.
(3) This parameter must be measured with bias voltages applied for less than 5 seconds to avoid overheating.
(4) ΔG_{ps} is defined as the change in G_{ps} from the value at V_{GG} = 7.0 volts (3N201) and V_{GG} = 6.0 volts (3N203).
(5) Power Gain Conversion

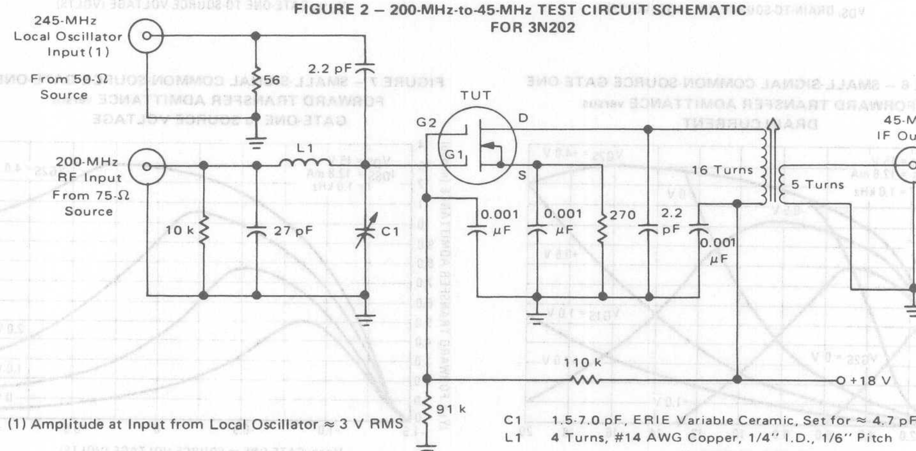
6

FIGURE 1 — 200-MHz TEST CIRCUIT SCHEMATIC FOR 3N201



C1 4.0-30 pF, ERIE Variable Ceramic, Set for ≈ 22 pF
C2 4.0-30 pF, ERIE Variable Ceramic, Set for ≈ 10 pF
L1 4 Turns, #14 AWG Cooper, 1/4" I.D., 1/6" Pitch
L2 3 Turns, #14 AWG Cooper, 1/4" I.D., 1/8" Pitch
RFC DELEVAN No. 153712, 1.0 μH

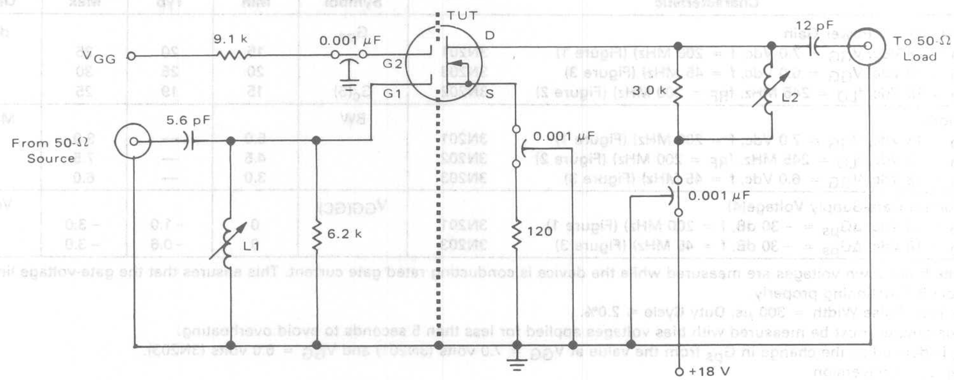
FIGURE 2 — 200-MHz-to-45-MHz TEST CIRCUIT SCHEMATIC FOR 3N202



(1) Amplitude at Input from Local Oscillator ≈ 3 V RMS

C1 1.5-7.0 pF, ERIE Variable Ceramic, Set for ≈ 4.7 pF
L1 4 Turns, #14 AWG Copper, 1/4" I.D., 1/6" Pitch

FIGURE 3 — 45-MHz TEST CIRCUIT SCHEMATIC
3N203



L1 14 Turns, #30 AWG Copper, Close-Wound 7/32" OD form with ARNOLD ENGINEERING "J" Tuning Core

L2 10 Turns, #30 AWG Copper, Close-Wound 7/32" OD form with ARNOLD ENGINEERING "J" Tuning Core

TYPICAL CHARACTERISTICS

FIGURE 4 — DRAIN CURRENT versus DRAIN to SOURCE VOLTAGE

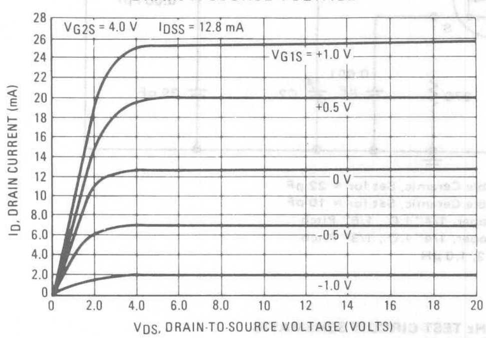


FIGURE 5 — DRAIN CURRENT versus GATE-ONE to SOURCE VOLTAGE

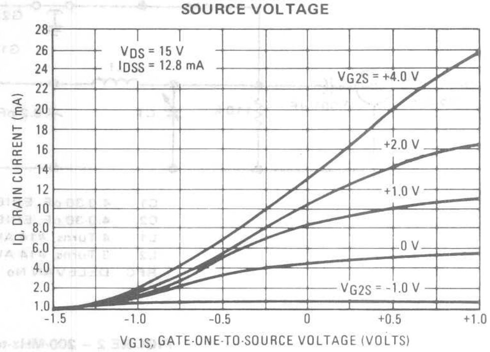


FIGURE 6 — SMALL-SIGNAL COMMON-SOURCE GATE-ONE FORWARD TRANSFER ADMITTANCE versus DRAIN CURRENT

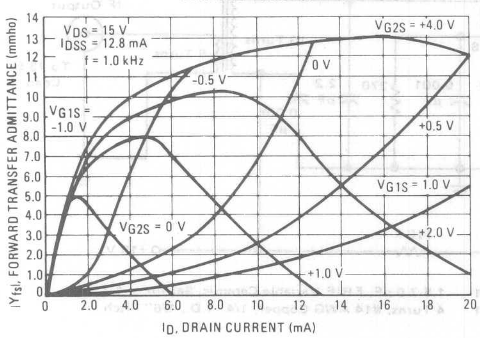


FIGURE 7 — SMALL-SIGNAL COMMON-SOURCE GATE-ONE FORWARD TRANSFER ADMITTANCE versus GATE-ONE to SOURCE VOLTAGE

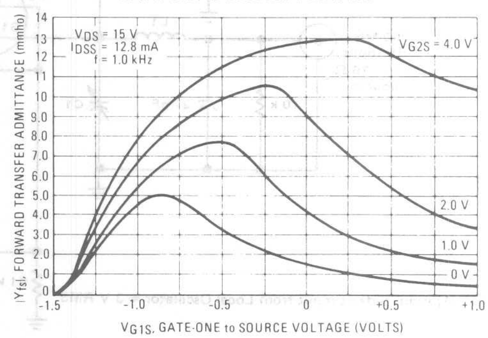


FIGURE 8 – SMALL-SIGNAL COMMON-SOURCE GATE-ONE FORWARD TRANSFER ADMITTANCE versus GATE-TWO to SOURCE VOLTAGE

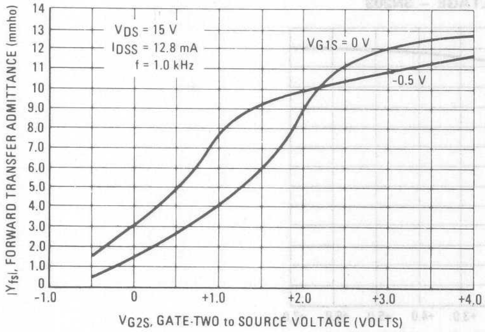
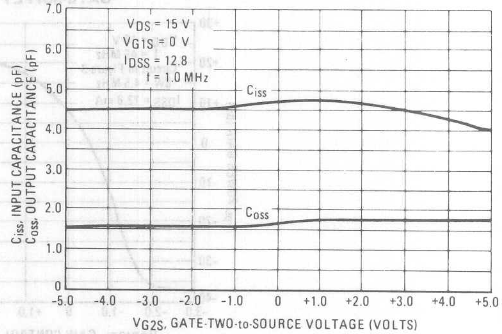


FIGURE 9 – SMALL-SIGNAL COMMON-SOURCE GATE-ONE INPUT AND OUTPUT CAPACITANCE versus GATE-TWO-to-SOURCE VOLTAGE



TYPICAL CHARACTERISTICS

FIGURE 10 – COMMON-SOURCE POWER GAIN AND SPOT NOISE FIGURE versus DRAIN CURRENT

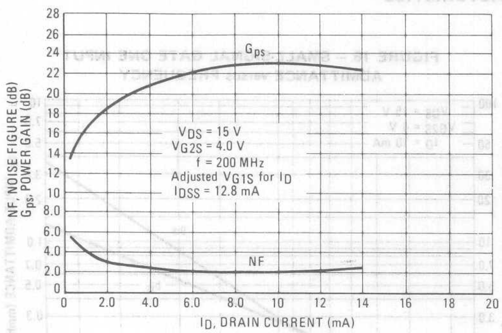


FIGURE 11 – COMMON-SOURCE POWER GAIN AND SPOT NOISE FIGURE versus GAIN CONTROL GATE-SUPPLY VOLTAGE – 3N201

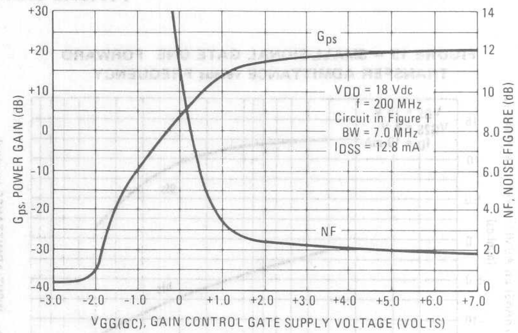


FIGURE 12 – COMMON-SOURCE POWER GAIN versus DRAIN SUPPLY CURRENT – 3N201

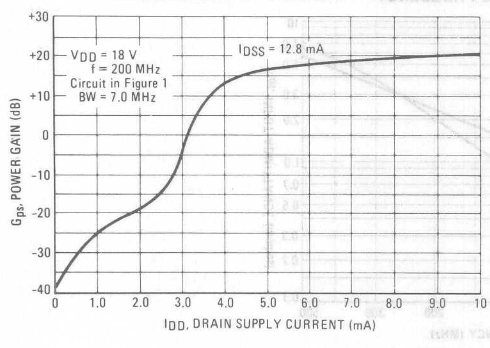


FIGURE 13 – SMALL-SIGNAL COMMON-SOURCE CONVERSION POWER GAIN versus LOCAL OSCILLATOR INPUT VOLTAGE – 3N202

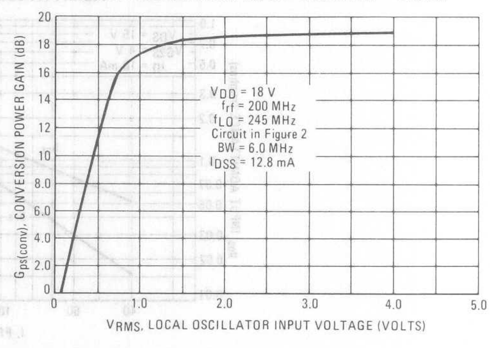
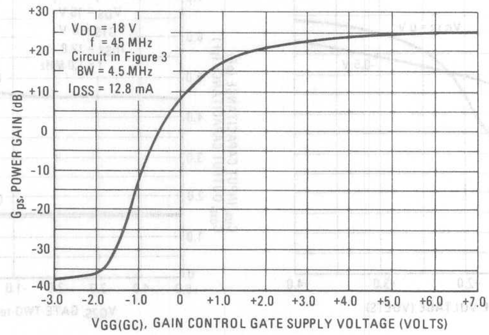


FIGURE 14 — SMALL-SIGNAL COMMON SOURCE INSERTION POWER GAIN versus GAIN CONTROL GATE-SUPPLY VOLTAGE — 3N203



TYPICAL CHARACTERISTICS

FIGURE 15 — SMALL-SIGNAL GATE ONE FORWARD TRANSFER ADMITTANCE versus FREQUENCY

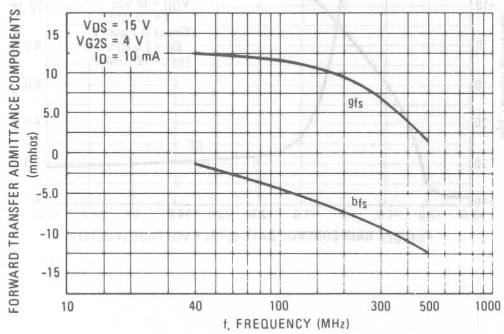


FIGURE 16 — SMALL-SIGNAL GATE ONE INPUT ADMITTANCE versus FREQUENCY

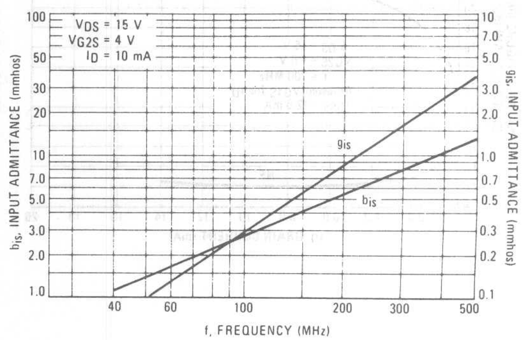
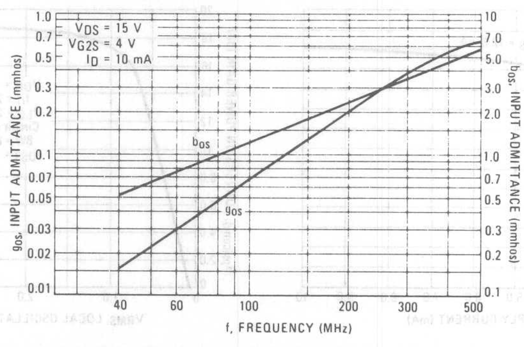
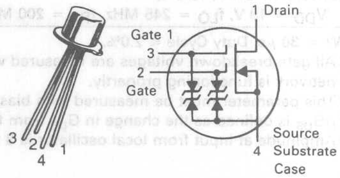


FIGURE 17 — SMALL-SIGNAL GATE ONE OUTPUT ADMITTANCE versus FREQUENCY



3N204
3N205

CASE 20-03, STYLE 9
TO-72 (TO-206AF)



DUAL-GATE MOSFET

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Drain Current	I_D	50	mA
Reverse Gate Current	I_G	−10	mA
Forward Gate Current	I_{GF}	10	mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	360 2.4	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.2 0.8	mW mW/°C
Lead Temperature	T_L	300	°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65°C to +175°C	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage ($I_D = 10\ \mu A$, $V_{G1} = V_{G2} = -5.0$ V)		$V_{(BR)DSX}$	25	—	Vdc
Gate 1-Source Breakdown Voltage ($I_{G1} = \pm 10$ mA) Note 1		$V_{(BR)G1SO}$	±6	±30	Vdc
Gate 2-Source Breakdown Voltage ($I_{G2} = \pm 10$ mA) Note 1		$V_{(BR)G2SO}$	±6	±30	Vdc
Gate 1 Leakage Current ($V_{G1S} = \pm 5.0$ V, $V_{G2S} = V_{DS} = 0$)		I_{G1SS}	—	±10	nA
Gate 2 Leakage Current ($V_{G2S} = \pm 5.0$ V, $V_{G1S} = V_{DS} = 0$)		I_{G2SS}	—	±10	nA
Gate 1 to Source Cutoff Voltage ($V_{DS} = 15$ V, $V_{G2S} = 4.0$ V, $I_D = 20\ \mu A$)		$V_{G1S(off)}$	−0.5	−4.0	Vdc
Gate 2 to Source Cutoff Voltage ($V_{DS} = 15$ V, $V_{G1S} = 0$ V, $I_D = 20\ \mu A$)		$V_{G2S(off)}$	−0.2	−4.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current* ($V_{DS} = 15$ V, $V_{G2S} = 4.0$ V, $V_{G1S} = 0$ V)		I_{DSS}*	6	30	mA
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance ($V_{DS} = 15$ V, $V_{G2S} = 4.0$ V, $V_{G1S} = 0$ V, f = 1.0 kHz) Note 2		$\lvert Y_{fs} \rvert$	10	22	mmhos
Input Capacitance ($V_{DS} = 15$ V, $V_{G2S} = 4.0$ V, $I_D = I_{DSS}$, f = 1.0 Mhz)		C_{iss}	Typ. 3.0		pF
Reverse Transfer Capacitance ($V_{DS} = 15$ V, $V_{G2S} = 4.0$ V, $I_D = 10$ mA, f = 1.0 MHz)		C_{rss}	0.005	0.03	pF
Output Capacitance ($V_{DS} = 15$ V, $V_{G2S} = 4.0$ V, $I_D = I_{DSS}$, f = 1.0 MHz)		C_{oss}	Typ. 1.4		pF
FUNCTIONAL CHARACTERISTICS					
Noise Figure ($V_{DD} = 18$ V, $V_{GG} = 7.0$ V, f = 200 MHz) ($V_{DS} = 15$ V, $V_{G2S} = 4.0$ V, $I_D = 10$ mA, f = 450 MHz)	 3N204 3N204	NF	 — —	 3.5 5.0	dB
Common Source Power Gain ($V_{DD} = 18$ V, $V_{GG} = 7.0$ V, f = 200 MHz) ($V_{DS} = 15$ V, $V_{G2S} = 4.0$ V, $I_D = 10$ mA, f = 450 MHz)	 3N204 3N204	G_{ps}	 20 14	 28 —	dB

6

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Bandwidth		BW			MHz
(V_{DD} = 18 V, V_{GG} = 7.0 V, f = 200 MHz)	3N3204		7.0	12	
(V_{DD} = 18 V, f_{LO} = 245 MHz, f_{RF} = 200 MHz) (Note 4)	3N205		4.0	7.0	
Gain Control Gate-Supply Voltage (Note 3)		$V_{GG(GC)}$	0	−2.0	Vdc
(V_{DD} = 18 V, ΔGPS = 300 dB, f = 200 MHz)	3N204				
Conversion Gain (Note 4)		$G_{(conv.)}$	17	28	dB
(V_{DD} = 18 V, f_{LO} = 245 MHz, f_{RF} = 200 MHz)	3N205				

*PW = 30 μs, Duty Cycle ≤ 2.0%.
(1) All gate breakdown voltages are measured while the device is conducting rated gate current. This insures that the gate voltage limiting network is functioning propertly.
(2) This parameter must be measured with bias voltages applied for less than five (5) seconds to avoid overheating.
(3) ΔG_{ps} is defined as the change in G_{ps} from the value at V_{GG} = 7.0 V.
(4) Amplitude at input from local oscillator is 3 volts RMS.

6

3N209

CASE 20-03, STYLE 9
TO-72 (TO-206AF)

DUAL-GATE MOSFET
UHF COMMUNICATIONS

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG1} V_{DG2}	30 30	Vdc
Drain Current	I_D	30	mAdc
Gate Current	I_{G1R} I_{G1F} I_{G2R} I_{G2F}	−10 10 −10 10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	 300 1.71	 mW mW/°C
Lead Temperature, 1/16″ From Seated Surface for 10 seconds	T_L	260	°C
Storage Channel Temperature Range	T_{stg}	−65 to +175	°C
Operating Channel Temperature	$T_{channel}$	175	°C

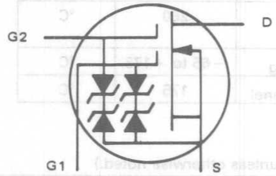
6

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (I_D = 10 μAdc, V_{G1S} = −4.0 Vdc, V_{G2S} = 4.0 Vdc)	$V_{(BR)DSX}$	25	—	—	Vdc
Gate 1 — Source Forward Breakdown Voltage (I_{G1} = 10 mAdc, V_{G2S} = V_{DS} = 0)	$V_{(BR)G1SSF}$	7.0	—	22	Vdc
Gate 1 — Source Reverse Breakdown Voltage (I_{G1} = −10 mAdc, V_{G2S} = V_{DS} = 0)	$V_{(BR)G1SSR}$	−7.0	—	−22	Vdc
Gate 2 — Source Forward Breakdown Voltage (I_{G2} = 10 mAdc, V_{G1S} = V_{DS} = 0)	$V_{(BR)G2SSF}$	7.0	—	22	Vdc
Gate 2 — Source Reverse Breakdown Voltage (I_{G2} = −10 mAdc, V_{G1S} = V_{DS} = 0)	$V_{(BR)G2SSR}$	−7.0	—	−22	Vdc
Gate 1 — Terminal Forward Current (V_{G1S} = 6.0 Vdc, V_{G2S} = V_{DS} = 0)	I_{G1SSF}	—	—	20	nAdc
Gate 1 — Terminal Reverse Current (V_{G1S} = −6.0 Vdc, V_{G2S} = V_{DS} = 0) (V_{G1S} = −6.0 Vdc, V_{G2S} = V_{DS} = 0, T_A = 150°C)	I_{G1SSR}	 — —	 — —	 −20 −10	 nAdc μAdc
Gate 2 — Terminal Forward Current (V_{G2S} = 6.0 Vdc, V_{G1S} = V_{DS} = 0)	I_{G2SSF}	—	—	20	nAdc
Gate 2 — Terminal Reverse Current (V_{G2S} = −6.0 Vdc, V_{G1S} = V_{DS} = 0) (V_{G2S} = −6.0 Vdc, V_{G1S} = V_{DS} = 0, T_A = 150°C)	I_{G2SSR}	 — —	 — —	 −20 −10	 nAdc μAdc
ON CHARACTERISTICS					
Gate 1 — Zero Voltage Drain Current (V_{DS} = 15 Vdc, V_{G1S} = 0, V_{G2S} = 4.0 Vdc)	I_{DSS}	5.0	—	30	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 10 mAdc, f = 1.0 kHz)	Y_{fs}	10	13	20	mmhos
Input Capacitance (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D ≥ 5.0 mAdc, f = 1.0 MHz)	C_{iss}	—	3.3	7.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D ≥ 5.0 mAdc, f = 1.0 MHz)	C_{rss}	0.005	0.023	0.03	pF
Output Capacitance (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D ≥ 5.0 mAdc, f = 1.0 MHz)	C_{oss}	0.5	2.0	4.0	pF

Characteristic	Symbol	Min	Typ	Max	Unit
FUNCTIONAL CHARACTERISTICS					
Noise Figure (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 10 mAdc, f = 500 MHz)	NF	—	4.0	6.0	dB
Common Source Power Gain (Figure 12) (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 10 mAdc, f = 500 MHz)	G_{ps}	10	13	20	dB
*Bandwidth (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 10 mAdc, f = 500 MHz)	BW	7.0	—	17	MHz

FIGURE 1 – MOSFET CIRCUIT SCHEMATIC



TYPICAL SCATTERING PARAMETERS

FIGURE 2 – S_{11}, INPUT REFLECTION COEFFICIENT versus FREQUENCY

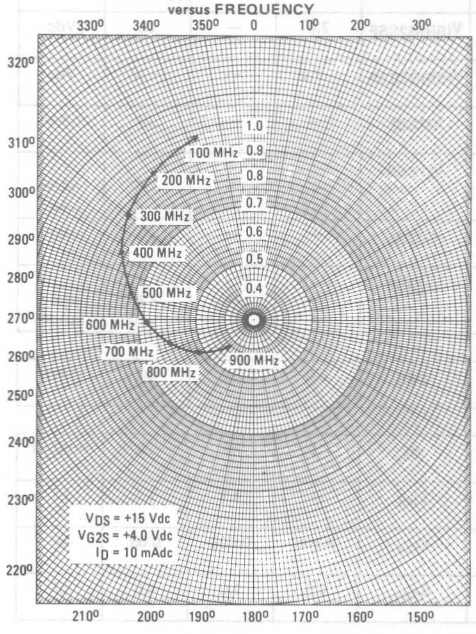
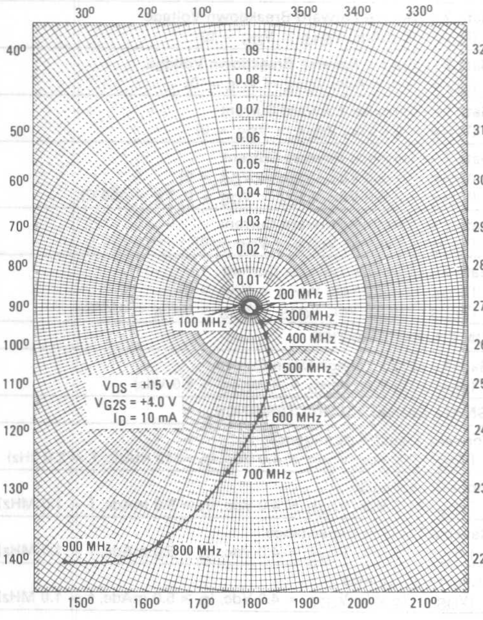
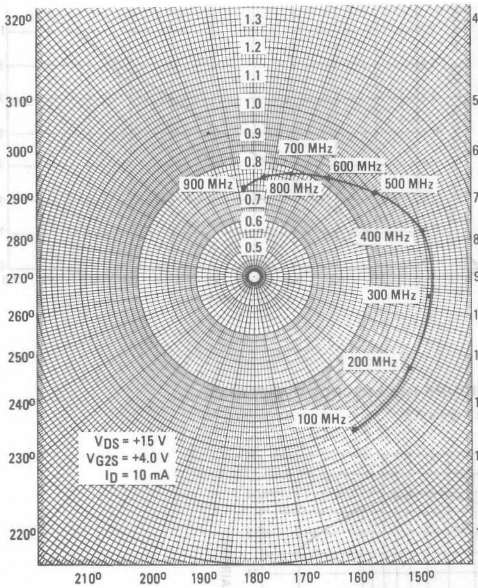
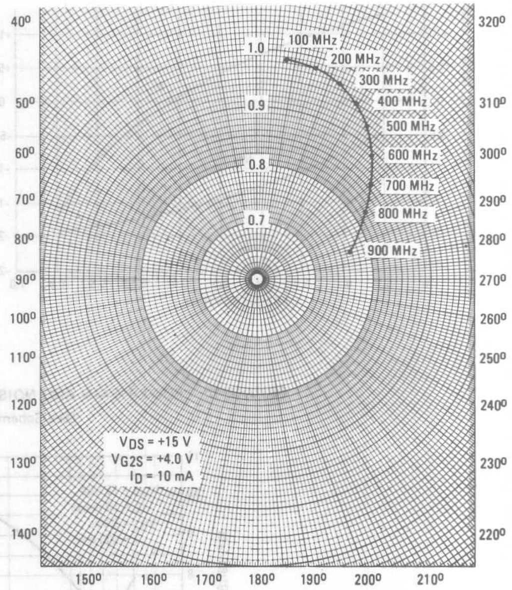


FIGURE 3 – S_{12}, REVERSE TRANSMISSION COEFFICIENT versus FREQUENCY







TYPICAL COMMON-SOURCE ADMITTANCE PARAMETERS

(V_{DS} = 15 Vdc, V_{GS2} = 4.0 Vdc, I_D = 10 mAdc)

FIGURE 6 – Y_{11}, INPUT ADMITTANCE versus FREQUENCY

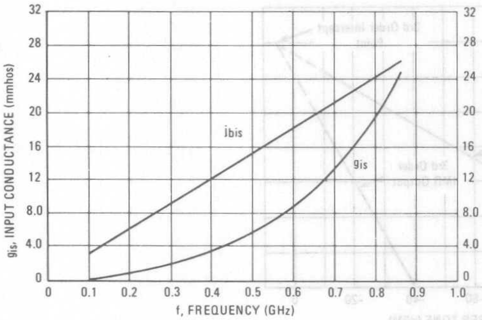


FIGURE 7 – Y_{12}, REVERSE TRANSFER ADMITTANCE versus FREQUENCY

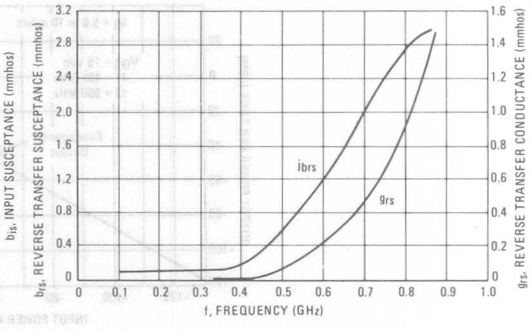


FIGURE 8 — Y_{21}, FORWARD TRANSFER ADMITTANCE versus FREQUENCY

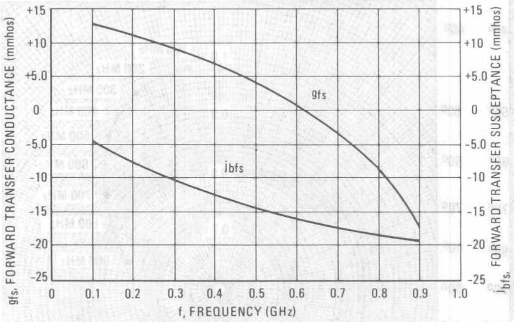


FIGURE 9 — Y_{22}, OUTPUT ADMITTANCE versus FREQUENCY

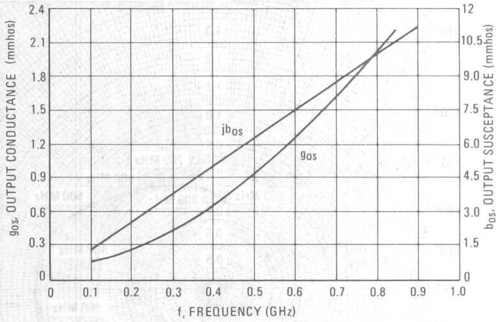
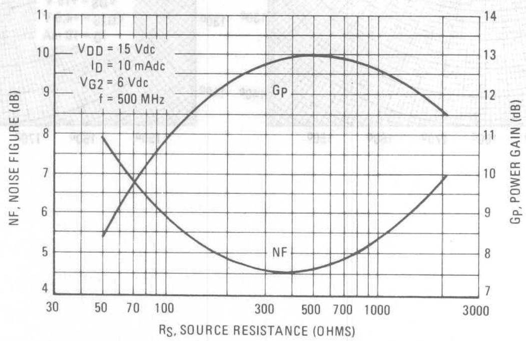


FIGURE 10 — POWER GAIN AND NOISE FIGURE versus SOURCE RESISTANCE

(See Schematic Figure 12)



The Test Circuit shown in Figure 12 was used to generate Power Gain and Noise Figure as a function of Source Resistance curves.

FIGURE 11 — THIRD ORDER INTERMODULATION DISTORTION

(See Schematic Figure 12)

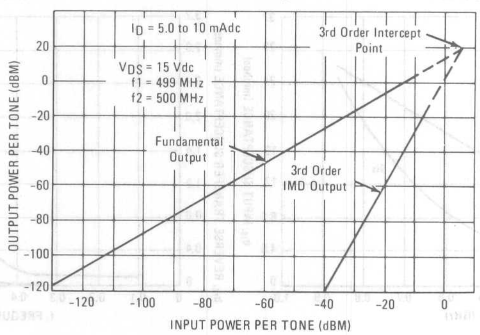
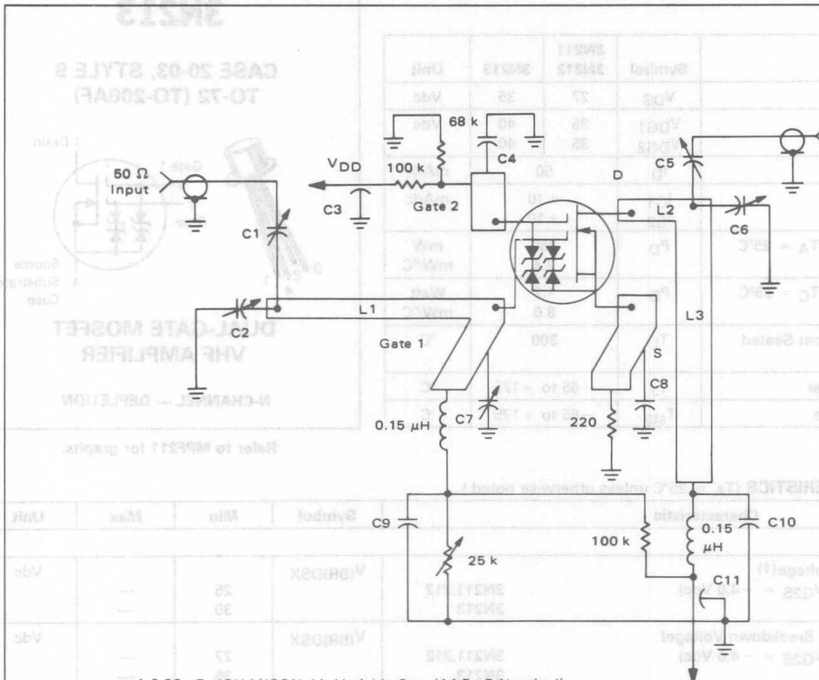


Figure 11 shows the typical third order intermodulation distortion (IMD) performance of the 3N209 and 3N210 at 500 MHz.

Both fundamental output and third order IMD output characteristics are plotted. The curves have been extrapolated to show the third order intermodulation output intercept point.

The performance is typical for I_D between 5.0 mAdc and 10 mAdc. The test circuit shown in Figure 12 was used to generate the IMD Data.

FIGURE 12 — TEST CIRCUIT FOR POWER GAIN, NOISE FIGURE AND THIRD ORDER INTERMODULATION DISTORTION



C1 = 1.0-20 pF, JOHANSON Air Variable Cap. (14.5 pF Nominal)
C2 = 1.0-10 pF, JOHANSON Air Variable Cap (5.4 pF Nominal)
C3, C11 = 470 pF, Low Inductance Feedthru Cap.
C4, C8, C9, C10 = 250 pF, Low Inductance, UNDERWOOD Cap. (J-101)
C5 = 0.4-6.0 pF, JOHANSON Air Variable Cap. (0.92 pF Nominal)
C6 = 1.0-10 pF, JOHANSON Air Variable Cap. (5.9 pF Nominal)
C7 = 1.0-10 pF, JOHANSON Air Variable Cap (3.0 pF Nominal)
L1 = 2.52 x 0.1 inches
L2 = 0.4 x 0.1 inches
L3 = 1.23 x 0.2 inches

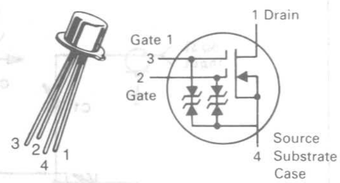
(L1, L2, L3) On 2 sided glass Teflon®, 1 oz. copper clad, 1/16″
$\epsilon_R = 2.55$

® Trademark of E.I. Dupont, DeNemours and Co., Inc.

6

3N211
3N212
3N213

CASE 20-03, STYLE 9
TO-72 (TO-206AF)



DUAL-GATE MOSFET
VHF AMPLIFIER

N-CHANNEL — DEPLETION

Refer to MPF211 for graphs.

MAXIMUM RATINGS

Rating	Symbol	3N211 3N212	3N213	Unit
Drain-Source Voltage	V_{DS}	27	35	Vdc
Drain-Gate Voltage	V_{DG1} V_{DG2}	35 35	40 40	Vdc
Drain Current	I_D	50		mAdc
Gate Current	I_{G1} I_{G2}	±10 ±10		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	360 2.4		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.2 8.0		Watt mW/°C
Lead Temperature, 1/16" From Seated Surface for 10 seconds	T_L	300		°C
Junction Temperature Range	T_J	−65 to +175		°C
Storage Temperature Range	T_{stg}	−65 to +175		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage(1) (I_D = 10 μAdc, V_{G1S} = V_{G2S} = −4.0 Vdc)	3N211,212 3N213	$V_{(BR)DSX}$	25 30	— —	Vdc
Instantaneous Drain-Source Breakdown Voltage) (I_D = 10 μAdc, V_{G1S} = V_{G2S} = −4.0 Vdc)	3N211,212 3N213	$V_{(BR)DSX}$	27 35	— —	Vdc
Gate 1-Source Breakdown Voltage(2) (I_{G1} = ±10 mAdc, V_{G2S} = V_{DS} = 0)		$V_{(BR)G1SO}$	±6.0	—	Vdc
Gate 2-Source Breakdown Voltage(2) (I_{G2} = ±10 mAdc, V_{G1S} = V_{DS} = 0)		$V_{(BR)G2SO}$	±6.0	—	Vdc
Gate 1 Leakage Current (V_{G1S} = ±5.0 Vdc, V_{G2S} = V_{DS} = 0) (V_{G1S} = −5.0 Vdc, V_{G2S} = V_{DS} = 0, T_A = 150°C)		I_{G1SS}	— —	±10 −10	nAdc μAdc
Gate 2 Leakage Current (V_{G2S} = ±5.0 Vdc, V_{G1S} = V_{DS} = 0) (V_{G2S} = −5.0 Vdc, V_{G1S} = V_{DS} = 0, T_A = 150°C)		I_{G2SS}	— —	±10 −10	nAdc μAdc
Gate 1 to Source Cutoff Voltage (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 20 μAdc)	3N211,213 3N212	$V_{G1S(off)}$	−0.5 −0.5	−5.5 −4.0	Vdc
Gate 2 to Source Cutoff Voltage (V_{DS} = 15 Vdc, V_{G1S} = 0, I_D = 20 μAdc)	3N211 3N212,213	$V_{G2S(off)}$	−0.2 −0.2	−2.5 −4.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current(3) (V_{DS} = 15 Vdc, V_{G1S} = 0, V_{G2S} = 4.0 Vdc)		I_{DSS}	6.0	40	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance(4) (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, V_{G1S} = 0, f = 1.0 kHz)	3N211,212 3N213	$\|y_{fs}\|$	17 15	40 35	mmhos
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 1.0 mAdc, f = 1.0 MHz)		C_{rss}	0.005	0.05	pF
FUNCTIONAL CHARACTERISTICS					
Noise Figure (V_{DD} = 18 Vdc, V_{GG} = 7.0 Vdc, f = 200 MHz) (V_{DD} = 24 Vdc, V_{GG} = 6.0 Vdc, f = 45 MHz)	3N211 3N211,13	NF	— —	3.5 4.0	dB

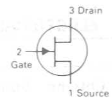
Characteristic	Device	Symbol	Min	Max	Unit
Common Source Power Gain		G_{ps}			dB
(V_{DD} = 18 Vdc, V_{GG} = 7.0 Vdc, f = 200 MHz)	3N211		24	35	
(V_{DD} = 24 Vdc, V_{GG} = 6.0 Vdc, f = 45 MHz)	3N211		29	37	
(V_{DD} = 24 Vdc, V_{GG} = 6.0 Vdc, f = 45 MHz)	3N213		27	35	
(V_{DD} = 18 Vdc, f_{LO} = 245 MHz, f_{RF} = 200 MHz)	3N212	G_c(6)	21	28	
Bandwidth		BW			MHz
(V_{DD} = 18 Vdc, V_{GG} = 7.0 Vdc, f = 200 MHz)	3N211		5.0	12	
(V_{DD} = 18 Vdc, f_{LO} = 245 MHz, f_{RF} = 200 MHz)	3N212		4.0	7.0	
(V_{DD} = 24 Vdc, V_{GG} = 6.0 Vdc, f = 45 MHz)	3N211,213		3.5	6.0	
Gain Control Gate-Supply Voltage(5)		$V_{GG(GC)}$			Vdc
(V_{DD} = 18 Vdc, ΔG_{ps} = −30 dB, f = 200 MHz)	3N211		—	−2.0	
(V_{DD} = 24 Vdc, ΔG_{ps} = −30 dB, f = 45 MHz)	2N211,213		—	±1.0	

(1) Measured after five seconds of applied voltage.
(2) All gate breakdown voltages are measured while the device is conducting rated gate current. This ensures that the gate-voltage limiting network is functioning properly.
(3) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.
(4) This parameter must be measured with bias voltages applied for less than 5 seconds to avoid overheating. The signal is applied to gate 1 with gate 2 at ac ground.
(5) ΔG_{ps} is defined as the change in G_{ps} from the value at V_{GG} = 7.0 Volts (3N211) and V_{GG} = 6.0 Volts (3N213).
(6) Power Gain Conversion. Amplitude at input from local oscillator is adjusted for maximum G_c.

6

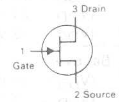
BF244,A,B,C

CASE 29-04, STYLE 22
TO-92 (TO-226AA)



BF245,A,B,C

CASE 29-04, STYLE 23
TO-92 (TO-226AA)



JFET
VHF/UHF AMPLIFIER

N-CHANNEL — DEPLETION

Refer to 2N4416 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	±30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage	V_{GS}	30	Vdc
Drain Current	I_D	100	mAdc
Forward Gate Current	$I_{G(f)}$	10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	360 2.88	mW mW/°C
Storage Channel Temperature Range	T_{stg}	−65 to +150	°C

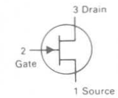
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Gate-Source Breakdown Voltage (I_G = 1.0 μAdc, V_{DS} = 0)		$V_{(BR)GSS}$	30	—	—	V
Gate-Source (V_{DS} = 15 Vdc, I_D = 200 μA)	BF245(1), BF244(2) BF245A, BF244A BF245B, BF244B BF245C, BF244C	V_{GS}	0.4 0.4 1.6 3.2	— — — —	7.5 2.2 3.8 7.5	V
Gate-Source Cutoff Voltage (V_{DS} = 15 Vdc, I_D = 10 nA)		$V_{GS(off)}$	0.5	—	8	V
Gate Reverse Current (V_{GS} = 20 Vdc, V_{DS} = 0)		I_{GSS}	—	—	5	nA
ON CHARACTERISTICS						
Zero-Gate Voltage Drain Current (V_{DS} = 15 Vdc, V_{GS} = 0)	BF245(1), BF244(2) BF245A, BF244A BF245B, BF244B BF245C, BF244C	I_{DSS}	2 2 6 12		25 6.5 15 25	mA
SMALL-SIGNAL CHARACTERISTICS						
Forward Transfer Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1 KHz)		$\|Y_{fs}\|$	3.0		6.5	mmhos
Output Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1 KHz)		$\|Y_{os}\|$		40		μmhos
Forward Transfer Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 200 MHz)		$\|Y_{fs}\|$		5.6		mmhos
Reverse Transfer Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 200 MHz)		$\|Y_{rs}\|$		1.0		mmhos
Input Capacitance (V_{DS} = 20 Vdc, $-V_{GS}$ = 1 Vdc)		C_{iss}		3		pF
Reverse Transfer Capacitance (V_{DS} = 20 Vdc, $-V_{GS}$ = 1 Vdc, f = 1 MHz)		C_{rss}		0.7		pF
Output Capacitance (V_{DS} = 20 Vdc, $-V_{GS}$ = 1 Vdc, f = 1 MHz)		C_{oss}		0.9		pF
Noise Figure (V_{DS} = 15 Vdc, V_{GS} = 0, R_G = 1 KΩ, f = 100 MHz)		N_F		1.5		db
Cut-off Frequency(3) (V_{DS} = 15 Vdc, V_{GS} = 0)		$F_{(Yfs)}$		700		MHz

(1) On orders against the BF245, any or all subgroups might be shipped.
(2) On orders against the BF244, any or all subgroups might be shipped.
(3) The frequency at which gfs is 0.7 of its value at 1 KHz.

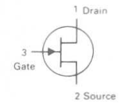
BF246,A,B,C

CASE 29-04, STYLE 22
TO-92 (TO-226AA)



BF247,A,B,C

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET SWITCHING

N-CHANNEL — DEPLETION

Refer to MPF4391 for graphs.

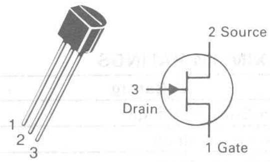
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	±25	Vdc
Drain-Gate Voltage	V_{DG}	25	Vdc
Gate-Source Voltage	V_{GS}	25	Vdc
Drain Current	I_D	100	mAdc
Forward Gate Current	$I_{G(f)}$	10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	360 2.88	mW mW/°C
Storage Channel Temperature Range	T_{stg}	−65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Gate-Source Breakdown Voltage (I_G = 1 μA, V_{DS} = 0)		$V_{(BR)GSS}$	25	—	—	V
Gate-Source (V_{DS} = 15 V, I_D = 200 μA)	BF246, BF247	V_{GS}	0.5		14	V
	BF246A, BF247A		1.5	—	4	
	BF246B, BF247B		3	—	7	
	BF246C, BF247C		5.5	—	12	
Gate-Source Cutoff Voltage (V_{DS} = 15 V, I_D = 10 nA)		$V_{GS(off)}$	0.6	—	14.5	V
Gate Cutoff Current (V_{GS} = 15 V, V_{DS} = 0)		I_{GSS}	—	—	5	nA
ON CHARACTERISTICS						
Zero-Gate Voltage Drain Current (V_{DS} = 15 V, V_{GS} = 0)	BF246, BF247	I_{DSS}	30		250	mA
	BF246A, BF247A		30		80	
	BF246B, BF247B		60		140	
	BF246C, BF247C		110		250	
SMALL-SIGNAL CHARACTERISTICS						
Forward Transfer Admittance (V_{DS} = 15 V, I_D = 10 mA, f = 1 kHz)		$\|Y_{fs}\|$	8	23		mmhos
Reverse Transfer Capacitance (V_{DS} = 15 V, I_D = 10 mA, f = 1 kHz)		C_{rss}		3.3		pF
Input Capacitance (V_{DS} = 15 V, I_D = 10 mA, f = 1 MHz)		C_{in}		6		pF
Output Capacitance (V_{DS} = 15 V, I_D = 10 mA, f = 1 MHz)		C_{out}		5		pF
Cutoff Frequency (V_{DS} = 15 V, V_{GS} = 0)		$F_{(Yfs)}$		450		MHz

CASE 29-04, STYLE 23
TO-92 (TO-226AA)



JFET
VHF/UHF AMPLIFIER
N-CHANNEL — DEPLETION

Refer to 2N4416 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	±30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage	V_{GS}	30	Vdc
Drain Current	I_D	100	mAdc
Forward Gate Current	$I_{G(f)}$	10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	360 2.88	mW mW/°C
Storage Channel Temperature Range	T_{stg}	−65 to +150	°C

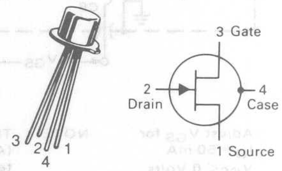
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = 1.0 μAdc, V_{DS} = 0)	$V_{(BR)GSS}$	30	—	—	Vdc
Gate-Source Voltage (V_{DS} = 15 Vdc, I_D = 200 μA)	$V_{GS(off)}$	0.5	—	7.5	Vdc
Gate Reverse Current (V_{GS} = 20 Vdc, V_{DS} = 0)	I_{GSS}	—	—	5	nAdc
ON CHARACTERISTICS					
Zero-Gate Voltage Drain Current) (V_{DS} = 15 Vdc, V_{GS} = 0)	I_{DSS}				mAdc
BF256(1)		3	—	18	
BF256A		3	—	7	
BF256B		6	—	13	
BF256C		11	—	18	
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1 kHz)	Y_{fs}	4.5	5	—	mmhos
Reverse Transfer Capacitance (V_{DS} = 20 Vdc, $-V_{GS}$ = 1Vdc, f = 1 MHz)	C_{rss}	—	0.7	—	pF
Output Capacitance (V_{DS} = 20 Vdc, V_{GS} = 0, f = 1 MHz)	C_{oss}	—	1.0	—	pF
Noise Figure (V_{DS} = 10 Vdc, R_s = 47Ω, f = 800 MHz)	N_F	—	7.5	—	db
Cut-off Frequency(2) (V_{DS} = 15 Vdc, V_{GS} = 0)	f_{gfs}	—	1000	—	MHz
Power Gain (V_{DS} = 15 Vdc, R_s = 47 Ω, f =800 MHz)	G_p	—	11	—	dB

(1) On orders against the BF256, any or all subgroups might be shipped.
(2) The frequency at which gfs is 0.7 of its value at 1 kHz.

BFW10
BFW11

CASE 20-03, STYLE 1
TO-72 (TO-206A)



JFET
VHF/UHF AMPLIFIER

N-CHANNEL — DEPLETION

Refer to 2N4416 for graphs.

6

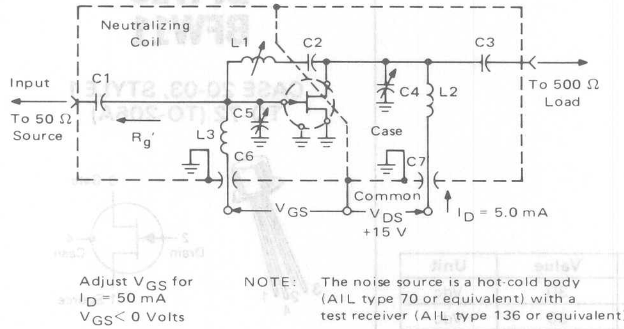
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Reverse Gate-Source Voltage	V_{GSR}	−30	Vdc
Forward Gate Current	I_{GF}	10	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	300 1.71	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Gate-Source Breakdown Voltage (I_G = 10 μAdc, V_{DS} = 0)		$V_{(BR)GSS}$	30	—	—	Vdc
Gate-Source Cutoff Voltage (V_{DS} = 15 Vdc, I_D = 0.5 nAdc)	BFW10 BFW11	$V_{GS(off)}$	—	—	8 6	Vdc
Gate Reverse Current (V_{GS} = 20 Vdc, V_{DS} = 0)		I_{GSS}	—	—	0.1	nAdc
Gate-Source Voltage (V_{DS} = 15 Vdc, I_D = 400 μAdc)	BFW10	V_{GS}	2	—	7.5	Vdc
Gate-Source Voltage (V_{DS} = 15 Vdc, I_D = 50 μAdc)	BFW11	V_{GS}	1.25	—	4	Vdc
ON CHARACTERISTICS						
Zero-Gate Voltage Drain Current (V_{DS} = 15 Vdc, V_{GS} = 0)	BFW10 BFW11	I_{DSS}	8 4	— —	20 10	mAdc
SMALL-SIGNAL CHARACTERISTICS						
Forward Transadmittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1 kHz)	BFW10 BFW11	Y_{fs}	3.5 3.0	— —	6.5 6.5	mmhos
Output Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)	BFW10 BFW11	Y_{os}	— —	— —	85 50	μmhos
Input Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0 Vdc, f = 1.0 MHz)		C_{iss}	—	—	5.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0 Vdc, f = 1.0 MHz)		C_{rss}	—	—	0.8	pF
Forward Transadmittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 200 MHz)		Y_{fs}	3.2	—	—	mmhos
Equivalent Noise Voltage (V_{DS} = 15 Vdc, V_{GS} = 0, f = 25 Hz)		e_n	—	—	75	$nV/\sqrt{Hz}$
Noise Figure (V_{DS} = 15 Vdc, V_{GS} = 0 V, see Figures 1, 2, 3)		NF	—	—	2.5	dB

FIGURE 1 – 100 MHz and 400 MHz NEUTRALIZED TEST CIRCUIT



NOTE: The noise source is a hot-cold body (AIL type 70 or equivalent) with a test receiver (AIL type 136 or equivalent).

Reference Designation	VALUE 100 MHz	400 MHz
C1	7.0 pF	1.8 pF
C2	1000 pF	17 pF
C3	3.0 pF	1.0 pF
C4	1-12 pF	0.8-8.0 pF
C5	1-12 pF	0.8-8.0 pF
C6	0.0015 μF	0.001 μF
C7	0.0015 μF	0.001 μF
L1	3.0 μH*	0.2 μH**
L2	0.15 μH*	0.03 μH**
L3	0.14 μH*	0.022 μH**

*L1 17 turns, (approx. – depends upon circuit layout) AWG #28 enameled copper wire, close wound on 9/32" ceramic coil form. Tuning provided by a powdered iron slug.

L2 4-1/2 turns, AWG #18 enameled copper wire, 5/16" long, 3/8" I.D. (AIR CORE).

L3 3-1/2 turns, AWG #18 enameled copper wire, 1/4" long, 3/8" I.D. (AIR CORE).

**L1 6 turns, (approx. – depends upon circuit layout) AWG #24 enameled copper wire, close wound on 7/32" ceramic coil form. Tuning provided by an aluminum slug.

L2 1 turn, AWG #16 enameled copper wire, 3/8" I.D. (AIR CORE).

L3 1/2 turn, AWG #16 enameled copper wire, 1/4" I.D. (AIR CORE).

NOISE FIGURE

($T_{channel}$ = 25°C)

FIGURE 2 – EFFECTS OF DRAIN-SOURCE VOLTAGE

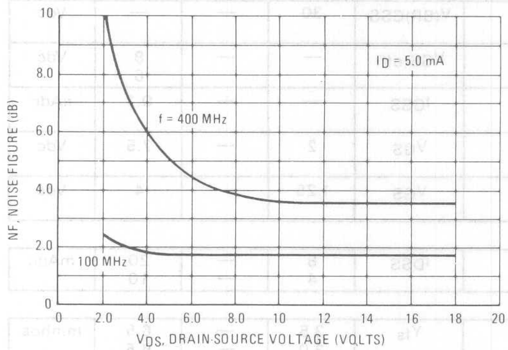
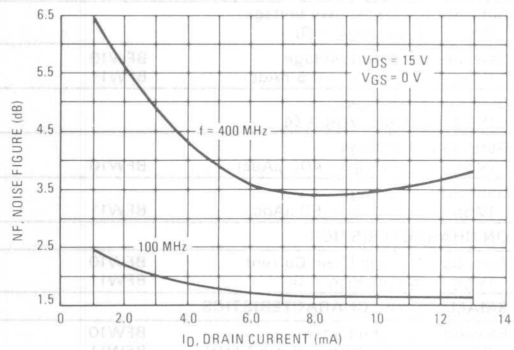
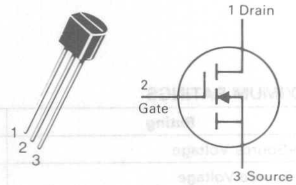


FIGURE 3 – EFFECTS OF DRAIN CURRENT



BS107,A

CASE 29-04, STYLE 30
TO-92 (TO-226AA)



TMOS
SWITCHING

N-CHANNEL — ENHANCEMENT

Refer to MFE9200 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	200	Vdc
Gate-Source Voltage	V_{GS}	±20	Vdc
Drain Current Continuous(1) Pulsed(2)	 I_D I_{DM}	 250 500	mAdc
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	0.6	Watts
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to 150	°C

(1) The Power Dissipation of the package may result in a lower continuous drain current.
(2) Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

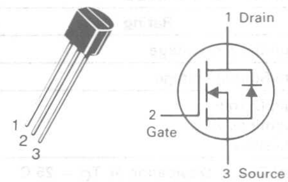
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Zero-Gate-Voltage Drain Current ($V_{DS} = 130$ V, $V_{GS} = 0$)	I_{DSS}	—	—	30	nAdc
Drain-Source Breakdown Voltage ($V_{GS} = 0$, $I_D = 100$ μA)	$V_{(BR)DSX}$	200	—	—	Vdc
Gate Reverse Current ($V_{GS} = 15$ Vdc, $V_{DS} = 0$)	I_{GSS}	—	0.01	10	nAdc
ON CHARACTERISTICS*					
Gate Threshold Voltage ($I_D = 1.0$ mA, $V_{DS} = V_{GS}$)	$V_{GS(Th)}$	1.0	—	3.0	Vdc
Static Drain-Source On Resistance BS107 ($V_{GS} = 2.6$ V, $I_D = 20$ mA) ($V_{GS} = 10$ V, $I_D = 200$ mA) BS107A ($V_{GS} = 10$ Vdc) ($I_D = 100$ mA) ($I_D = 250$ mA)	$r_{DS(on)}$	 — — — —	 — — 4.5 4.8	 28 14 6.0 6.4	Ohms
SMALL-SIGNAL CHARACTERISTICS					
Input Capacitance ($V_{DS} = 25$ V, $V_{GS} = 0$, f = 1.0 MHz)	C_{iss}	—	60	—	pF
Reverse Transfer Capacitance ($V_{DS} = 25$ V, $V_{GS} = 0$, f = 1.0 MHz)	C_{rss}	—	6.0	—	pF
Output Capacitance ($V_{DS} = 25$ V, $V_{GS} = 0$, f = 1.0 MHz)	C_{oss}	—	30	—	pF
Forward Transconductance ($V_{DS} = 25$ V, $I_D = 250$ mA)	g_{fs}	200	400	—	mmhos
SWITCHING CHARACTERISTICS					
Turn-On Time	t_{on}	—	6.0	15	ns
Turn-Off Time	t_{off}	—	12	15	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

BS170

CASE 29-04, STYLE 30
TO-92 (TO-226AA)



TMOS FET SWITCHING

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	Vdc
Gate-Source Voltage	V_{GS}	±20	Vdc
Drain Current(1)	I_D	0.5	Adc
Total Device Dissipation @ T_C = 25°C	P_D	0.83	Watt
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

(1) The Power Dissipation of the package may result in a lower continuous drain current.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Gate Reverse Current (V_{GS} = 15 V, V_{DS} = 0)	I_{GSS}	—	0.01	10	nAdc
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 100 μA)	$V_{(BR)DSS}$	60	90	—	Vdc
ON CHARACTERISTICS(2)					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.0 mA)	$V_{GS(Th)}$	0.8	2.0	3.0	Vdc
Static Drain-Source On Resistance (V_{GS} = 10 V, I_D = 200 mA)	$r_{DS(on)}$	—	1.8	5.0	Ohms
Drain Cutoff Current (V_{DS} = 25 V, V_{GS} = 0 V)	$I_{D(off)}$	—	—	0.5	μA
Forward Transconductance (V_{DS} = 10 V, I_D = 250 mA)	g_{fs}	—	200	—	mmhos
SMALL-SIGNAL CHARACTERISTICS					
Input Capacitance (V_{DS} = 10 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	60	—	pF
SWITCHING CHARACTERISTICS					
Turn-On Time (I_D = 0.2 A) See Figure 1	t_{on}	—	4.0	10	ns
Turn-Off Time (I_D = 0.2 A) See Figure 1	t_{off}	—	4.0	10	ns

(2) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — SWITCHING TEST CIRCUIT

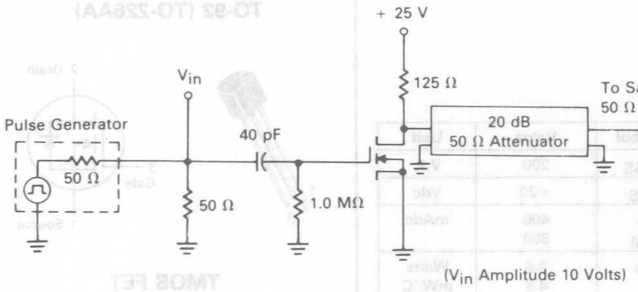


FIGURE 2 — SWITCHING WAVEFORMS

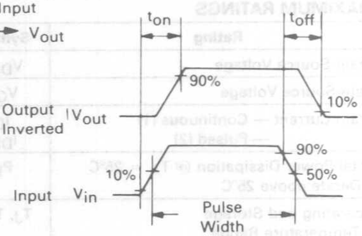


FIGURE 3 — $V_{GS(th)}$ NORMALIZED versus TEMPERATURE

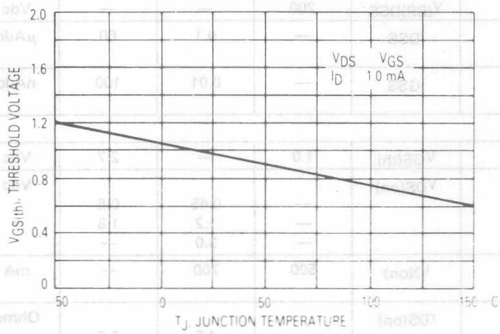


FIGURE 4 — ON-REGION CHARACTERISTICS

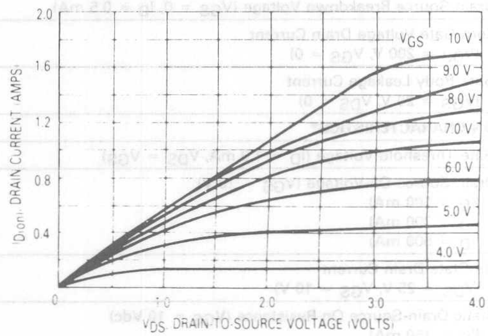


FIGURE 5 — OUTPUT CHARACTERISTICS

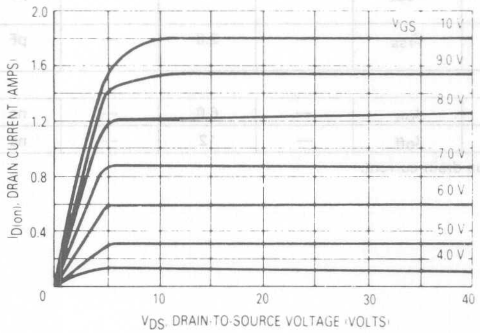
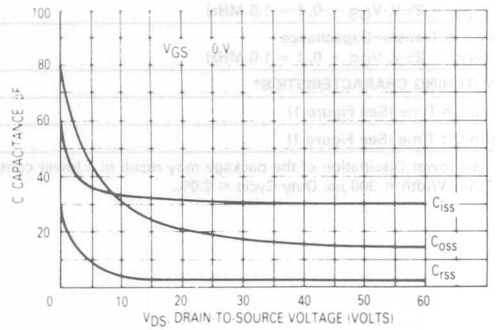
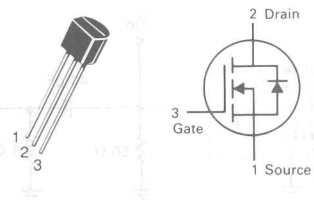


FIGURE 6 — CAPACITANCE versus DRAIN-TO-SOURCE VOLTAGE



BSS89

CASE 29-04, STYLE 7
TO-92 (TO-226AA)



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	200	Vdc
Gate-Source Voltage	V_{GS}	±20	Vdc
Drain Current — Continuous (1) — Pulsed (2)	I_D I_{DM}	400 800	mAdc
Total Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.6 4.8	Watts mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150	°C
Thermal Resistance Junction to Ambient	θ_{JA}	208	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage ($V_{GS} = 0$, $I_D = 0.5$ mA)	$V_{(BR)DSS}$	200	—	—	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = 200$ V, $V_{GS} = 0$)	I_{DSS}	—	0.1	60	μAdc
Gate-Body Leakage Current ($V_{GS} = 20$ V, $V_{DS} = 0$)	I_{GSS}	—	0.01	100	nAdc
ON CHARACTERISTICS*					
Gate Threshold Voltage ($I_D = 1.0$ mA, $V_{DS} = V_{GS}$)	$V_{GS(th)}$	1.0	—	2.7	Vdc
Drain-Source On-Voltage ($V_{GS} = 10$ V) ($I_D = 100$ mA) ($I_D = 300$ mA) ($I_D = 500$ mA)	$V_{DS(on)}$	 — — —	 0.45 1.2 3.0	 0.6 1.8 —	Vdc
On-State Drain Current ($V_{DS} = 25$ V, $V_{GS} = 10$ V)	$I_{D(on)}$	500	700	—	mA
Static Drain-Source On-Resistance ($V_{GS} = 10$ Vdc) ($I_D = 150$ mA) ($I_D = 300$ mA) ($I_D = 500$ mA)	$r_{DS(on)}$	 — — —	 4.5 — 6.0	 6.0 6.0 —	Ohms
Forward Transconductance ($V_{DS} = 25$ V, $I_D = 300$ mA)	g_{fs}	140	400	—	mmhos
DYNAMIC CHARACTERISTICS					
Input Capacitance ($V_{DS} = 25$ V, $V_{GS} = 0$, f = 1.0 MHz)	C_{iss}	—	72	—	pF
Output Capacitance ($V_{DS} = 25$ V, $V_{GS} = 0$, f = 1.0 MHz)	C_{oss}	—	15	—	pF
Reverse Transfer Capacitance ($V_{DS} = 25$ V, $V_{GS} = 0$, f = 1.0 MHz)	C_{rss}	—	2.8	—	pF
SWITCHING CHARACTERISTICS*					
Turn-On Time (See Figure 1)	t_{on}	—	6.0	—	ns
Turn-Off Time (See Figure 1)	t_{off}	—	12	—	ns

(1) The Power Dissipation of the package may result in a lower continuous drain current.
(2) Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

RESISTIVE SWITCHING

FIGURE 1 — SWITCHING TEST CIRCUIT

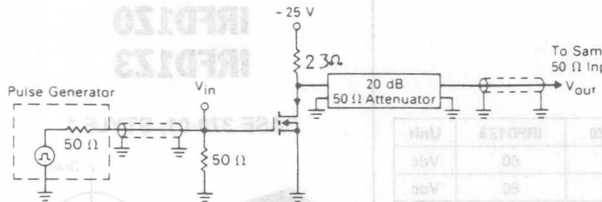


FIGURE 2 — SWITCHING WAVEFORMS

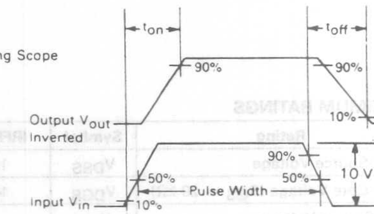


FIGURE 3 — ON VOLTAGE versus TEMPERATURE

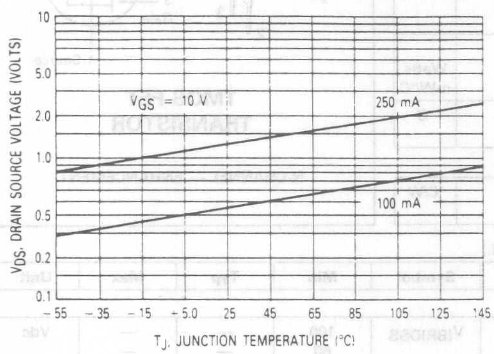


FIGURE 4 — CAPACITANCE VARIATION

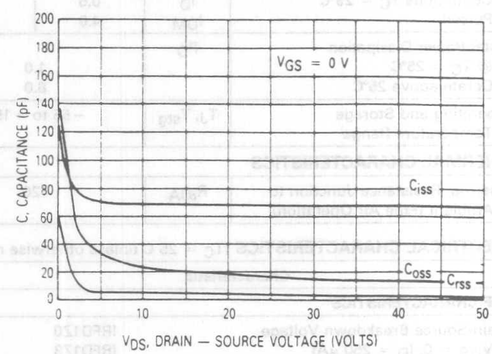


FIGURE 5 — TRANSFER CHARACTERISTIC

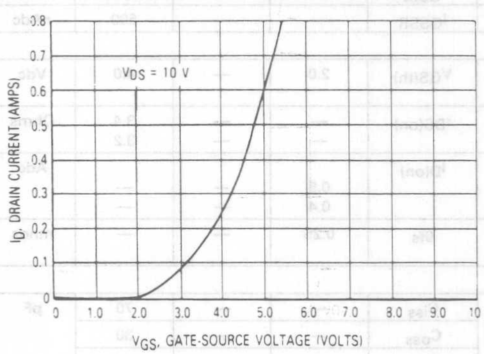


FIGURE 6 — OUTPUT CHARACTERISTIC

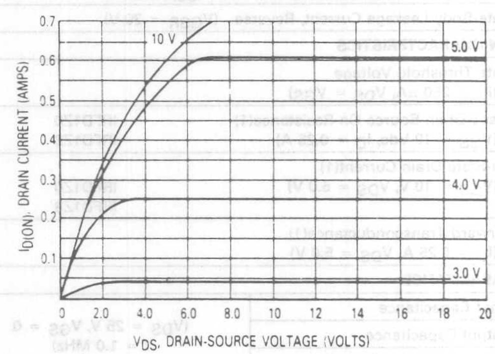
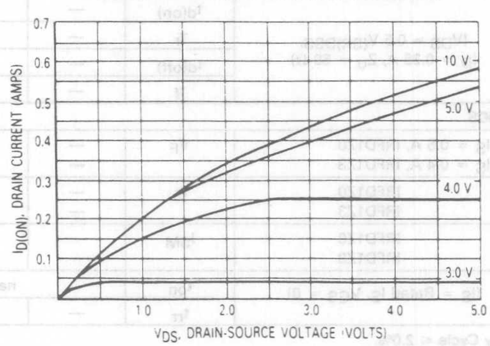
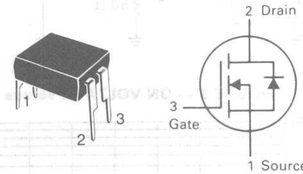


FIGURE 7 — SATURATION CHARACTERISTIC



IRFD1Z0
IRFD1Z3

CASE 370-01, STYLE 1



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	IRFD1Z0	IRFD1Z3	Unit
Drain-Source Voltage	V_{DSS}	100	60	Vdc
Drain-Gate Voltage (R_{GS} = 20 kΩ)	V_{DGR}	100	60	Vdc
Gate-Source Voltage	V_{GS}	±20		Vdc
Drain Current Continuous T_C = 25°C Pulsed	 I_D I_{DM}	 0.5 4.0	 0.4 3.2	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	 1.0 8.0		 Watts mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Ambient (Free Air Operation)	$R_{\theta JA}$	120	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

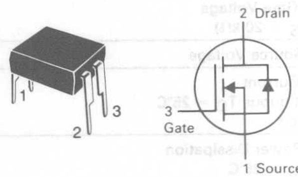
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 250 μA)	IRFD1Z0 IRFD1Z3	$V_{(BR)DSS}$	100 60	— —	— —	Vdc
Zero Gate Voltage Drain Current (V_{DSS} = Rated V_{DSS}, V_{GS} = 0 V)		I_{DSS}	—	—	250	μAdc
Gate-Body Leakage Current, Forward (V_{GSF} = 20 V)		I_{GSSF}	—	—	500	nAdc
Gate-Body Leakage Current, Reverse (V_{GSR} = 20 V)		I_{GSSR}	—	—	500	nAdc
ON CHARACTERISTICS						
Gate Threshold Voltage (I_D = 250 μA, V_{DS} = V_{GS})		$V_{GS(th)}$	2.0	—	4.0	Vdc
Static Drain-Source On-Resistance(1) (V_{GS} = 10 Vdc, I_D = 0.25 A)	IRFD1Z0 IRFD1Z3	$r_{DS(on)}$	— —	— —	3.4 3.2	Ohms
On-State Drain Current(1) (V_{GS} = 10 V, V_{DS} = 5.0 V)	IRFD1Z0 IRFD1Z3	$I_{D(on)}$	0.5 0.4	— —	— —	Adc
Forward Transconductance(1) (I_D = 0.25 A, V_{DS} = 5.0 V)		g_{fs}	0.25	—	—	mhos
CAPACITANCE						
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0 f = 1.0 MHz)	C_{iss}	—	—	70	pF
Output Capacitance		C_{oss}	—	—	30	
Reverse Transfer Capacitance		C_{rss}	—	—	10	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	(V_{DS} ≈ 0.5 $V_{(BR)DSS}$, I_D = 0.25 A, Z_o = 50 Ω)	$t_{d(on)}$	—	—	20	ns
Rise Time		t_r	—	—	25	
Turn-Off Delay Time		$t_{d(off)}$	—	—	25	
Fall Time		t_f	—	—	20	
SOURCE-DRAIN DIODE CHARACTERISTICS						
Diode Forward Voltage (V_{GS} = 0)(1)	I_S = 0.5 A, IRFD1Z0 I_S = 0.4 A, IRFD1Z3	V_F	— —	— —	1.4 1.3	Vdc
Continuous Source Current, Body Diode	IRFD1Z0 IRFD1Z3	I_S	— —	— —	0.5 0.4	Adc
Pulsed Source Current, Body Diode	IRFD1Z0 IRFD1Z3	I_{SM}	— —	— —	4.0 3.2	A
Forward Turn-On Time	(I_S = Rated I_S, V_{GS} = 0)	t_{on}	negligible			ns
Reverse Recovery Time		t_{rr}	—	100	—	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

6

IRFD113

CASE 370-01, STYLE 1



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	IRFD110	IRFD113	Unit
Drain-Source Voltage	V_{DSS}	100	60	Vdc
Drain-Gate Voltage (R_{GS} = 20 kΩ)	V_{DGR}	100	60	Vdc
Gate-Source Voltage	V_{GS}	±20		Vdc
Drain Current Continuous T_C = 25°C Pulsed	 I_D I_{DM}	 1.0 8.0	 0.8 6.4	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	 1.0 8.0		Watts mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Ambient	$R_{\theta JA}$	120	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

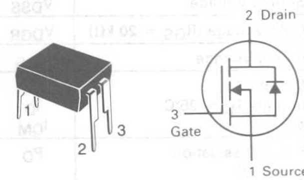
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 250 μA)	IRFD110 IRFD113	$V_{(BR)DSS}$	100 60	— —	— —	Vdc
Zero Gate Voltage Drain Current (V_{DSS} = Rated V_{DSS}, V_{GS} = 0 V)		I_{DSS}	—	—	250	μAdc
Gate-Body Leakage Current, Forward (V_{GSF} = 20 V)		I_{GSSF}	—	—	500	nAdc
Gate-Body Leakage Current, Reverse (V_{GSR} = −20 V)		I_{GSSR}	—	—	−500	nAdc
ON CHARACTERISTICS						
Gate Threshold Voltage (I_D = 250 μA, V_{DS} = V_{GS})		$V_{GS(th)}$	2.0	—	4.0	Vdc
Static Drain-Source On-Resistance(1) (V_{GS} = 10 Vdc, I_D = 0.8 A)	IRFD110 IRFD113	$r_{DS(on)}$	— —	— —	0.6 0.8	Ohms
On-State Drain Current(1) (V_{GS} = 10 V, V_{DS} = 5.0 V)	IRFD110 IRFD113	$I_{D(on)}$	1.0 0.8	— —	— —	Adc
Forward Transconductance(1) (I_D = 0.8 A, V_{DS} = 5.0 V)		g_{fs}	0.8	—	—	mhos
CAPACITANCE						
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0 f = 1.0 MHz)	C_{iss}	—	—	200	pF
Output Capacitance		C_{oss}	—	—	100	
Reverse Transfer Capacitance		C_{rss}	—	—	25	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	(V_{DS} ≈ 0.5 $V_{(BR)DSS}$, I_D = 0.8 A, Z_o = 50 Ω)	$t_{d(on)}$	—	—	20	ns
Rise Time		t_r	—	—	25	
Turn-Off Delay Time		$t_{d(off)}$	—	—	25	
Fall Time		t_f	—	—	20	
SOURCE-DRAIN DIODE CHARACTERISTICS						
Diode Forward Voltage (V_{GS} = 0)	I_S = 1.0 A, IRFD110 I_S = 0.8 A, IRFD113	V_F	—	—	2.5 2.0	Vdc
Continuous Source Current, Body Diode	IRFD110 IRFD113	I_S	— —	— —	1.0 0.8	Adc
Pulsed Source Current, Body Diode	IRFD110 IRFD113	I_{SM}	— —	— —	8.0 6.4	A
Forward Turn-On Time	(I_S = Rated I_S, V_{GS} = 0)	t_{on}		negligible		ns
Reverse Recovery Time		t_{rr}	—	100		

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

6

IRFD120
IRFD123

CASE 370-01, STYLE 1



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	IRFD120	IRFD123	Unit
Drain-Source Voltage	V_{DSS}	100	60	Vdc
Drain-Gate Voltage (R_{GS} = 20 kΩ)	V_{DGR}	100	60	Vdc
Gate-Source Voltage	V_{GS}	±20		Vdc
Drain Current Continuous T_C = 25°C Pulsed	I_D I_{DM}	1.3 5.2	1.1 4.4	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0		Watts mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Ambient	$R_{\theta JA}$	120	°C/W

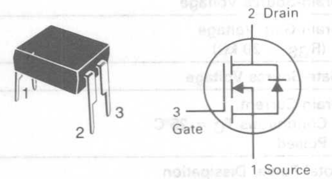
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 250 μA)	IRFD120 IRFD123	$V_{(BR)DSS}$	100 60	— —	— —	Vdc
Zero Gate Voltage Drain Current (V_{DSS} = Rated V_{DSS}, V_{GS} = 0 V)		I_{DSS}	—	—	250	μAdc
Gate-Body Leakage Current, Forward (V_{GSF} = 20 V)		I_{GSSF}	—	—	500	nAdc
Gate-Body Leakage Current, Reverse (V_{GSR} = −20 V)		I_{GSSR}	—	—	−500	nAdc
ON CHARACTERISTICS						
Gate Threshold Voltage (I_D = 250 μA, V_{DS} = V_{GS})		$V_{GS(th)}$	2.0	—	4.0	Vdc
Static Drain-Source On-Resistance(1) (V_{GS} = 10 Vdc, I_D = 0.6 A)	IRFD120 IRFD123	$r_{DS(on)}$	— —	— —	0.3 0.4	Ohms
On-State Drain Current(1) (V_{GS} = 10 V, V_{DS} = 5.0 V)	IRFD120 IRFD123	$I_{D(on)}$	1.3 1.1	— —	— —	Adc
Forward Transconductance(1) (I_D = 0.6 A, V_{DS} = 5.0 V)		g_{fs}	0.9	—	—	mhos
CAPACITANCE						
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0 f = 1.0 MHz)	C_{iss}	—	—	600	pF
Output Capacitance		C_{oss}	—	—	400	
Reverse Transfer Capacitance		C_{rss}	—	—	100	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	(V_{DS} ≈ 0.5 $V_{(BR)DSS}$, I_D = 0.6 A, Z_o = 50 Ω)	$t_{d(on)}$	—	—	40	ns
Rise Time		t_r	—	—	70	
Turn-Off Delay Time		$t_{d(off)}$	—	—	100	
Fall Time		t_f	—	—	70	
SOURCE-DRAIN DIODE CHARACTERISTICS						
Diode Forward Voltage (V_{GS} = 0)	I_S = 1.3 A, IRFD120 I_S = 1.1 A, IRFD123	V_{SD}	— —	— —	2.5 2.3	Vdc
Continuous Source Current, Body Diode	IRFD120 IRFD123	I_S	— —	— —	1.3 1.1	Adc
Pulsed Source Current, Body Diode	IRFD120 IRFD123	I_{SM}	— —	— —	5.2 4.4	A
Forward Turn-On Time	(I_S = Rated I_S, V_{GS} = 0)	t_{on}		negligible		ns
Reverse Recovery Time		t_{rr}	—	280	—	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

IRFD210
IRFD213

CASE 370-01, STYLE 1



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	IRFD210	IRFD213	Unit
Drain-Source Voltage	V_{DSS}	200	150	Vdc
Drain-Gate Voltage (R_{GS} = 20 kΩ)	V_{DGR}	200	150	Vdc
Gate-Source Voltage	V_{GS}	±20		Vdc
Drain Current Continuous T_C = 25°C Pulsed	 I_D I_{DM}	 0.6 2.5	 0.45 1.8	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	 1.0 0.008		 Watts mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	120	°C/W

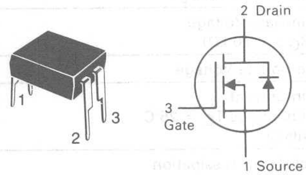
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 250 μA) IRFD210 IRFD213	$V_{(BR)DSS}$	 200 150	 — —	 — —	Vdc
Zero Gate Voltage Drain Current (V_{DSS} = Rated V_{DSS}, V_{GS} = 0 V)	I_{DSS}	—	—	250	μAdc
Gate-Body Leakage Current, Forward (V_{GSF} = 20 V)	I_{GSSF}	—	—	500	nAdc
Gate-Body Leakage Current, Reverse (V_{GSR} = −20 V)	I_{GSSR}	—	—	500	nAdc
ON CHARACTERISTICS					
Gate Threshold Voltage (I_D = 250 μA, V_{DS} = V_{GS})	$V_{GS(th)}$	2.0	—	4.0	Vdc
Static Drain-Source On-Resistance(1) (V_{GS} = 10 Vdc, I_D = 0.3 A) IRFD210 IRFD213	$r_{DS(on)}$	 — —	 — —	 1.5 2.4	Ohms
On-State Drain Current(1) (V_{GS} = 10 V, V_{DS} = 5.0 V) IRFD210, IRFD211 IRFD212, IRFD213	$I_{D(on)}$	 1.5 2.4	 — —	 — —	Adc
Forward Transconductance(1) (I_D = 0.3 A, V_{DS} = 5.0 V)	g_{fs}	0.5	—	—	mhos
CAPACITANCE					
Input Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	—	150	pF
Output Capacitance	C_{oss}	—	—	80	
Reverse Transfer Capacitance	C_{rss}	—	—	25	
SWITCHING CHARACTERISTICS					
Turn-On Delay Time (V_{DS} ≈ 0.5 $V_{(BR)DSS}$, I_D = 0.3 A, Z_o = 50 Ω)	$t_{d(on)}$	—	—	15	ns
Rise Time	t_r	—	—	25	
Turn-Off Delay Time	$t_{d(off)}$	—	—	15	
Fall Time	t_f	—	—	15	
SOURCE-DRAIN DIODE CHARACTERISTICS					
Diode Forward Voltage (V_{GS} = 0) I_S = 0.6 A, IRFD210 I_S = 0.45 A, IRFD213	V_{SD}	 —	 —	2.0 1.8	Vdc
Continuous Source Current, Body Diode IRFD210 IRFD213	I_S	— —	— —	0.6 0.45	Adc
Pulsed Source Current, Body Diode IRFD210 IRFD213	I_{SM}	— —	— —	2.5 1.8	A
Forward Turn-On Time (I_S = Rated I_S, V_{GS} = 0)	t_{on}		negligible		ns
Reverse Recovery Time	t_{rr}	—	290	—	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

IRFD223

CASE 370-01, STYLE 1



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

6

MAXIMUM RATINGS

Rating	Symbol	IRFD220	IRFD223	Unit
Drain-Source Voltage	V_{DSS}	200	150	Vdc
Drain-Gate Voltage (R_{GS} = 20 kΩ)	V_{DGR}	200	150	Vdc
Gate-Source Voltage	V_{GS}	±20		Vdc
Drain Current Continuous T_C = 25°C Pulsed	 I_D I_{DM}	 0.8 2.4	 0.7 5.6	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	 1.0 0.008		 Watts mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Ambient	$R_{\theta JA}$	120	°C/W

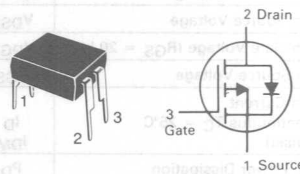
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 250 μA)	IRFD220 IRFD223	$V_{(BR)DSS}$	200 150	— —	— —	Vdc
Zero Gate Voltage Drain Current (V_{DSS} = Rated V_{DSS}, V_{GS} = 0 V)		I_{DSS}	—	—	250	μAdc
Gate-Body Leakage Current, Forward (V_{GSF} = 20 V)		I_{GSSF}	—	—	500	nAdc
Gate-Body Leakage Current, Reverse (V_{GSR} = −20 V)		I_{GSSR}	—	—	−500	nAdc
ON CHARACTERISTICS						
Gate Threshold Voltage (I_D = 250 μA, V_{DS} = V_{GS})		$V_{GS(th)}$	2.0	—	4.0	Vdc
Static Drain-Source On-Resistance(1) (V_{GS} = 10 Vdc, I_D = 0.4 A)	IRFD220 IRFD223	$r_{DS(on)}$	— —	— —	0.8 1.2	Ohms
On-State Drain Current(1) (V_{GS} = 10 V, V_{DS} = 5.0 V)	IRFD220 IRFD223	$I_{D(on)}$	0.8 0.7	— —	— —	Adc
Forward Transconductance(1) (I_D = 0.4 A, V_{DS} = 5.0 V)		g_{fs}	0.5	—		mhos
CAPACITANCE						
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0 f = 1.0 MHz)	C_{iss}	—	—	600	pF
Output Capacitance		C_{oss}	—	—	300	
Reverse Transfer Capacitance		C_{rss}	—	—	80	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	(V_{DS} ≈ 0.5 $V_{(BR)DSS}$, I_D = 0.4 A, Z_o = 50 Ω)	$t_{d(on)}$	—	—	40	ns
Rise Time		t_r	—	—	60	
Turn-Off Delay Time		$t_{d(off)}$	—	—	100	
Fall Time		t_f	—	—	60	
SOURCE-DRAIN DIODE CHARACTERISTICS						
Diode Forward Voltage (V_{GS} = 0)	I_S = 0.8 A, IRFD220 I_S = 0.7 A, IRFD223	V_{SD}	— —	— —	2.0 1.8	Vdc
Continuous Source Current, Body Diode	IRFD220 IRFD223	I_S	— —	— —	0.8 0.7	Adc
Pulsed Source Current, Body Diode	IRFD220 IRFD223	I_{SM}	— —	— —	6.4 5.6	A
Forward Turn-On Time	(I_S = Rated I_S, V_{GS} = 0)	t_{on}	negligible			ns
Reverse Recovery Time		t_{rr}	—	150	—	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

IRFD9110
IRFD9112

CASE 370-01, STYLE 1



TMOS FET TRANSISTOR

P-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	IRFD9110	IRFD9112	Unit
Drain-Source Voltage	V_{DSS}	−100		Vdc
Drain-Gate Voltage (R_{GS} = 20 kΩ)	V_{DGR}	−100		Vdc
Gate-Source Voltage	V_{GS}	±20		Vdc
Drain Current Continuous T_C = 25°C Pulsed	I_D I_{DM}	−0.7 −3.0	−0.6 −2.5	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0		Watts mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Rating	Symbol	IRFD9110	IRFD9112	Unit
Thermal Resistance Junction to Ambient (Free Air Operation)	$R_{\theta JA}$	120		°C/W

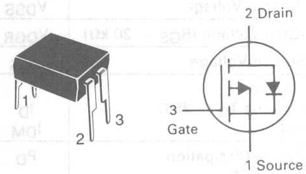
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = −250 μA)		$V_{(BR)DSS}$	100			Vdc
Zero Gate Voltage Drain Current (V_{DSS} = Rated V_{DSS}, V_{GS} = 0 V)		I_{DSS}	—	—	250	μAdc
Gate-Body Leakage Current, Forward (V_{GSF} = −20 V)		I_{GSSF}	—	—	500	nAdc
Gate-Body Leakage Current, Reverse (V_{GSR} = 20 V)		I_{GSSR}	—	—	500	nAdc
ON CHARACTERISTICS						
Gate Threshold Voltage (I_D = −250 μA, V_{DS} = V_{GS})		$V_{GS(th)}$	2.0	—	4.0	Vdc
Static Drain-Source On-Resistance(1) (V_{GS} = −10 Vdc, I_D = −0.3 A)	IRFD9110 IRFD9112	$r_{DS(on)}$	— —		1.2 1.6	Ohms
On-State Drain Current(1) (V_{GS} = 10 V, V_{DS} = −5.0 V)	IRFD9110 IRFD9112	$I_{D(on)}$	0.7 0.6	— —		Adc
Forward Transconductance(1) (I_D = −0.3 A, V_{DS} = −5.0 V)		g_{fs}	0.6	—	—	mhos
CAPACITANCE						
Input Capacitance	(V_{DS} = −25 V, V_{GS} = 0 f = 1.0 MHz)	C_{iss}	—	—	250	pF
Output Capacitance		C_{oss}	—	—	100	
Reverse Transfer Capacitance		C_{rss}	—	—	35	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	(V_{DS} ≈ 0.5 $V_{(BR)DSS}$, I_D = −0.3 A, Z_o = 50 Ω)	$t_{d(on)}$	—	—	30	ns
Rise Time		t_r	—	—	60	
Turn-Off Delay Time		$t_{d(off)}$	—	—	40	
Fall Time		t_f	—	—	40	
SOURCE-DRAIN DIODE CHARACTERISTICS						
Diode Forward Voltage (V_{GS} = 0)	I_S = −0.7 A, IRFD9110 I_S = −0.6 A, IRFD9112	V_{SD}	— —	— —	−5.5 −5.3	Vdc
Continuous Source Current, Body Diode	IRFD9110 IRFD9112	I_S	— —	— —	−0.7 −0.6	Adc
Pulsed Source Current, Body Diode	IRFD9110 IRFD9112	I_{SM}	— —	— —	−3.0 −2.5	A
Forward Turn-On Time	(I_S = Rated I_S, V_{GS} = 0)	t_{on}		negligible		ns
Reverse Recovery Time		t_{rr}	—	120	—	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

IRFD9120
IRFD9123

CASE 370-01, STYLE 1



TMOS FET TRANSISTOR

P-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	IRFD9120	IRFD9123	Unit
Drain-Source Voltage	V_{DSS}	100	60	Vdc
Drain-Gate Voltage (R_{GS} = 20 kΩ)	V_{DGR}	100	60	Vdc
Gate-Source Voltage	V_{GS}	±20		Vdc
Drain Current Continuous T_C = 25°C Pulsed	 I_D I_{DM}	 1.0 8.0	 0.8 6.4	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	 1.0 8.0		 Watts mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Ambient (Free Air Operation)	$R_{\theta JA}$	120		°C/W

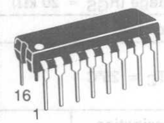
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = −250 μA)	IRFD9120 IRFD9123	$V_{(BR)DSS}$	100 60	— —	— —	Vdc
Zero Gate Voltage Drain Current (V_{DSS} = Rated V_{DSS}, V_{GS} = 0 V)		I_{DSS}	—	—	250	μAdc
Gate-Body Leakage Current, Forward (V_{GSF} = −20 V)		I_{GSSF}	—	—	500	nAdc
Gate-Body Leakage Current, Reverse (V_{GSR} = 20 V)		I_{GSSR}	—	—	500	nAdc
ON CHARACTERISTICS						
Gate Threshold Voltage (I_D = −250 μA, V_{DS} = V_{GS})		$V_{GS(th)}$	2.0	—	4.0	Vdc
Static Drain-Source On-Resistance(1) (V_{GS} = −10 Vdc, I_D = −0.8 A)	IRFD9120 IRFD9123	$r_{DS(on)}$	— —		0.6 0.8	Ohms
On-State Drain Current(1) (V_{GS} = 10 V, V_{DS} = −5.0 V)	IRFD9120 IRFD9123	$I_{D(on)}$	1.0 0.8	— —	— —	Adc
Forward Transconductance(1) (I_D = −0.8 A, V_{DS} = −5.0 V)		g_{fs}	0.8		—	mhos
CAPACITANCE						
Input Capacitance	(V_{DS} = −25 V, V_{GS} = 0 f = 1.0 MHz)	C_{iss}	—	—	450	pF
Output Capacitance		C_{oss}	—	—	350	
Reverse Transfer Capacitance		C_{rss}	—	—	100	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	(V_{DS} ≈ 0.5 $V_{(BR)DSS}$, I_D = −0.8 A, Z_o = 50 Ω)	$t_{d(on)}$	—	—	50	ns
Rise Time		t_r	—	—	100	
Turn-Off Delay Time		$t_{d(off)}$	—	—	100	
Fall Time		t_f	—	—	100	
SOURCE-DRAIN DIODE CHARACTERISTICS						
Diode Forward Voltage (V_{GS} = 0)	I_S = −1.0 A, IRFD9120 I_S = −0.8 A, IRFD9123	V_F	— —	— —	6.3 6.0	Vdc
Continuous Source Current, Body Diode	IRFD9120 IRFD9123	I_S	— —	— —	1.0 0.8	Adc
Pulsed Source Current, Body Diode	IRFD9120 IRFD9123	I_{SM}	— —	— —	8.0 6.4	A
Forward Turn-On Time	(I_S = Rated I_S, V_{GS} = 0)	t_{on}	negligible			ns
Reverse Recovery Time		t_{rr}	—	150	—	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

IRFE110
IRFE113

CASE 648-06



QUAD TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	IRFE110	IRFE113	Unit
Drain-Source Voltage	V_{DSS}	100	60	Vdc
Drain-Gate Voltage (R_{GS} = 20 kΩ)	V_{DGR}	100	60	Vdc
Gate-Source Voltage	V_{GS}	±20		Vdc
Drain Current Continuous T_C = 25°C Pulsed	 I_D I_{DM}	 1.0 8.0	 0.8 6.4	Adc
Total Power Dissipation @ T_C = 25°C — Package	P_D	3.0		Watts
Derate above 25°C — Package		30		mW/°C
Total Power Dissipation @ T_C = 25°C — Per Device		1.0		Watt
Derate above 25°C — Per Device		8.0		mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance Junction to Ambient (Free Air Operation)	$R_{\theta JA}$	40 Total Package 125 Each FET	°C/W

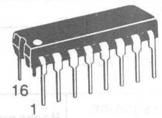
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS EACH FET						
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 250 μA)	IRFE110 IRFE113	$V_{(BR)DSS}$	100 60	— —	— —	Vdc
Zero Gate Voltage Drain Current (V_{DSS} = Rated V_{DSS}, V_{GS} = 0 V)		I_{DSS}	—	—	250	μAdc
Gate-Body Leakage Current, Forward (V_{GSF} = 20 V)		I_{GSSF}	—	—	500	nAdc
Gate-Body Leakage Current, Reverse (V_{GSR} = −20 V)		I_{GSSR}	—	—	500	nAdc
ON CHARACTERISTICS EACH FET						
Gate Threshold Voltage (I_D = 250 μA, V_{DS} = V_{GS})		$V_{GS(th)}$	2.0	—	4.0	Vdc
Static Drain-Source On-Resistance(1) (V_{GS} = 10 Vdc, I_D = 0.8 A)	IRFE110 IRFE113	$r_{DS(on)}$	— —	— —	0.6 0.8	Ohms
On-State Drain Current(1) (V_{GS} = 10 V, V_{DS} = 5.0 V)	IRFE110 IRFE113	$I_{D(on)}$	1.0 0.8	— —		Adc
Forward Transconductance(1) (I_D = 0.8 A, V_{DS} = 5.0 V)		g_{fs}	0.8	—		mhos
CAPACITANCE EACH FET						
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0 f = 1.0 MHz)	C_{iss}	—	—	200	pF
Output Capacitance		C_{oss}	—	—	100	
Reverse Transfer Capacitance		C_{rss}	—	—	25	
SWITCHING CHARACTERISTICS EACH FET						
Turn-On Delay Time	(V_{DS} ≈ 0.5 $V_{(BR)DSS}$, I_D = 0.8 A, Z_o = 50 Ω)	$t_{d(on)}$	—	—	20	ns
Rise Time		t_r	—	—	25	
Turn-Off Delay Time		$t_{d(off)}$	—	—	25	
Fall Time		t_f	—	—	20	
SOURCE-DRAIN DIODE CHARACTERISTICS EACH FET						
Diode Forward Voltage (V_{GS} = 0)	I_S = 1.0 A, IRFE110 I_S = 0.8 A, IRFE113	V_F	— —	— —	2.5 2.0	Vdc
Continuous Source Current, Body Diode	IRFE110 IRFE113	I_S	— —	— —	1.0 0.8	Adc
Pulsed Source Current, Body Diode	IRFE110 IRFE113	I_{SM}	— —	— —	8.0 6.4	A
Forward Turn-On Time	(I_S = Rated I_S, V_{GS} = 0)	t_{on}	negligible			ns
Reverse Recovery Time		t_{rr}	—	100	—	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

IRFE9120
IRFE9123

CASE 648-06



QUAD TMOS FET TRANSISTOR

P-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating		Symbol	IRFE9120	IRFE9123	Unit
Drain-Source Voltage		V_{DSS}	100	60	Vdc
Drain-Gate Voltage (R_{GS} = 20 kΩ)		V_{DGR}	100	60	Vdc
Gate-Source Voltage		V_{GS}	±20		Vdc
Drain Current Continuous T_C = 25°C Pulsed		 I_D I_{DM}	 1.0 8.0	 0.8 6.4	Adc
Total Power Dissipation @ T_C = 25°C	Package	P_D	3.0 30		Watts mW/°C
Derate above 25°C	Per Device		1.0 8.0		Watt mW/°C
Operating and Storage Temperature Range		T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Ambient (Free Air Operation)	$R_{\theta JA}$	40 Total Package 125 Each FET	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS EACH FET						
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = −250 μA)	IRFE9120 IRFE9123	$V_{(BR)DSS}$	100 60	— —	— —	Vdc
Zero Gate Voltage Drain Current (V_{DSS} = Rated V_{DSS}, V_{GS} = 0 V)		I_{DSS}	—	—	250	μAdc
Gate-Body Leakage Current, Forward (V_{GSF} = 20 V)		I_{GSSF}	—	—	500	nAdc
Gate-Body Leakage Current, Reverse (V_{GSR} = −20 V)		I_{GSSR}	—	—	500	nAdc
ON CHARACTERISTICS EACH FET						
Gate Threshold Voltage (I_D = −250 μA, V_{DS} = V_{GS})		$V_{GS(th)}$	2.0	—	4.0	Vdc
Static Drain-Source On-Resistance(1) (V_{GS} = −10 Vdc, I_D = −0.8 A)	IRFE9120 IRFE9123	$r_{DS(on)}$	— —	— —	0.6 0.8	Ohms
On-State Drain Current(1) (V_{GS} = −10 V, V_{DS} = 5.0 V)	IRFE9120 IRFE9123	$I_{D(on)}$	1.0 0.8	— —	— —	Adc
Forward Transconductance(1) (I_D = −0.8 A, V_{DS} = 5.0 V)		g_{fs}	0.8	—	—	mhos
CAPACITANCE EACH FET						
Input Capacitance	(V_{DS} = −25 V, V_{GS} = 0 f = 1.0 MHz)	C_{iss}	—	—	450	pF
Output Capacitance		C_{oss}	—	—	350	
Reverse Transfer Capacitance		C_{rss}	—	—	100	
SWITCHING CHARACTERISTICS EACH FET						
Turn-On Delay Time	(V_{DS} ≈ 0.5 $V_{(BR)DSS}$, I_D = −0.8 A, Z_o = 50 Ω)	$t_{d(on)}$	—	—	50	ns
Rise Time		t_r	—	—	100	
Turn-Off Delay Time		$t_{d(off)}$	—	—	100	
Fall Time		t_f	—	—	100	
SOURCE-DRAIN DIODE CHARACTERISTICS EACH FET						
Diode Forward Voltage (V_{GS} = 0)	I_S = −1.0 A, IRFE9120 I_S = −0.8 A, IRFE9123	V_F	— —	— —	6.3 6.0	Vdc
Continuous Source Current, Body Diode	IRFE9120 IRFE9123	I_S	— —	— —	1.0 0.8	Adc
Pulsed Source Current, Body Diode	IRFE9120 IRFE9123	I_{SM}	— —	— —	8.0 6.4	A
Forward Turn-On Time	(I_S = Rated I_S, V_{GS} = 0)	t_{on}	negligible			ns
Reverse Recovery Time		t_{rr}	—	150	—	

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MAXIMUM RATINGS

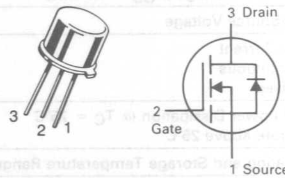
Rating	Symbol	IRFF110	IRFF113	Unit
Drain-Source Voltage	V_{DSS}	100	60	Vdc
Drain-Gate Voltage (R_{GS} = 1.0 mΩ)	V_{DGR}	100	60	Vdc
Gate-Source Voltage	V_{GS}	±20		Vdc
Drain Current Continuous Pulsed	 I_D I_{DM}	 3.5 14	 3.0 12	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	15 0.12		Watts W/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150		°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Case	$R_{\theta JC}$	8.33	°C/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	175	°C/W
Maximum Lead Temperature 1.6 mm from Case for 10 s	T_L	300	°C

IRFF113

CASE 79-03, STYLE 6
TO-39 (TO-205AF)



TMOS FET
TRANSISTOR

N-CHANNEL — ENHANCEMENT

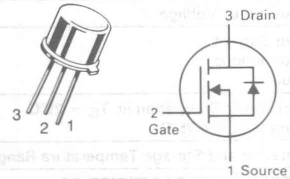
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 250 μA)	IRFF110 IRFF113	$V_{(BR)DSS}$	100 60	— —	Vdc
Zero Gate Voltage Drain Current (V_{DS} = Rated V_{DSS}, V_{GS} = 0)		I_{DSS}	—	250	μAdc
Gate-Body Leakage Current, Forward (V_{GS} = 20 Vdc, V_{DS} = 0)		I_{GSSF}	—	100	nAdc
Gate-Body Leakage Current, Reverse (V_{GS} = −20 Vdc, V_{DS} = 0)		I_{GSSR}	—	100	nAdc
ON CHARACTERISTICS*					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μA)		$V_{GS(th)}$	2.0	4.0	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 1.5 Adc)	IRFF110 IRFF113	$r_{DS(on)}$	— —	0.6 0.8	Ohm
On-State Drain Current (V_{GS} = 10 Vdc, V_{DS} = 15 V)	IRFF110 IRFF113	$I_{D(on)}$	3.5 3.0	— —	A
Forward Transconductance (I_D = 1.5 A, V_{DS} = 15 V)		g_{fs}	1.0	—	mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	200	pF
Output Capacitance		C_{oss}	—	100	
Reverse Transfer Capacitance		C_{rss}	—	25	
SWITCHING CHARACTERISTICS*					
Turn-On Delay Time	(V_{DD} = 0.5 Rated V_{DSS}, I_D = 1.5 A, R_{gen} = 50 ohms)	$t_{d(on)}$	—	20	ns
Rise Time		t_r	—	25	
Turn-Off Delay Time		$t_{d(off)}$	—	25	
Fall Time		t_f	—	20	
SOURCE-DRAIN DIODE CHARACTERISTICS*					
Forward On-Voltage	IRFF110	V_{SD}	—	2.5	Vdc
	IRFF113	V_{SD}	—	2.0	Vdc
Forward Turn-On Time	(I_S = Rated $I_{D(on)}$, V_{GS} = 0)	t_{on}	—	Negligible	ns
Reverse Recovery Time		t_{rr}	—	200 (Typ)	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

IRFF120
IRFF123

CASE 79-03, STYLE 6
TO-39 (TO-205AF)



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	IRFF120	IRFF123	Unit
Drain-Source Voltage	V_{DSS}	100	60	Vdc
Drain-Gate Voltage (R_{GS} = 1.0 mΩ)	V_{DGR}	100	60	Vdc
Gate-Source Voltage	V_{GS}	±20		Vdc
Drain Current Continuous Pulsed	 I_D I_{DM}	 6.0 24	 5.0 20	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	20 0.16		Watts W/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta JC}$	6.25	°C/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	175	°C/W
Maximum Lead Temperature 1.6 mm from Case for 10 s	T_L	300	°C

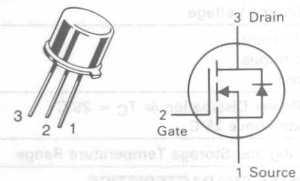
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 250 μA)	IRFF120 IRFF123	$V_{(BR)DSS}$	100 60	— —	Vdc
Zero Gate Voltage Drain Current (V_{DS} = Rated V_{DSS}, V_{GS} = 0)		I_{DSS}	—	250	μAdc
Gate-Body Leakage Current, Forward (V_{GS} = 20 Vdc, V_{DS} = 0)		I_{GSSF}	—	100	nAdc
Gate-Body Leakage Current, Reverse (V_{GS} = 20 Vdc, V_{DS} = 0)		I_{GSSR}	—	−100	nAdc
ON CHARACTERISTICS*					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μA)		$V_{GS(th)}$	2.0	4.0	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 3.0 Adc)	IRFF120 IRFF123	$r_{DS(on)}$	— —	0.3 0.4	Ohm
On-State Drain Current (V_{GS} = 10 V, V_{DS} = 15 V)	IRFF120 IRFF123	$I_{D(on)}$	6.0 5.0	— —	A
Forward Transconductance (I_D = 3.0 A, V_{DS} = 15 V)		g_{fs}	1.5		mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	600	pF
Output Capacitance		C_{oss}	—	400	
Reverse Transfer Capacitance		C_{rss}	—	100	
SWITCHING CHARACTERISTICS*					
Turn-On Delay Time	(V_{DD} ≈ 0.5 Rated V_{DSS}, I_D = 3.0 A, R_{gen} = 50 ohms)	$t_{d(on)}$	—	40	ns
Rise Time		t_r	—	70	
Turn-Off Delay Time		$t_{d(off)}$	—	100	
Fall Time		t_f	—	70	
SOURCE-DRAIN DIODE CHARACTERISTICS*					
Forward On-Voltage	IRFF120	V_{SD}	—	2.5	Vdc
	IRFF123	V_{SD}	—	2.3	Vdc
Forward Turn-On Time	(I_S = Rated $I_{D(on)}$, V_{GS} = 0)	t_{on}	—	Negligible	ns
Reverse Recovery Time		t_{rr}	—	200 (Typ)	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

IRFF210
IRFF213

CASE 79-03
TO-39 (TO-205AF)



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

6

MAXIMUM RATINGS

Rating	Symbol	IRFF210	IRFF213	Unit
Drain-Source Voltage	V_{DSS}	200	150	Vdc
Drain-Gate Voltage (R_{GS} = 1.0 mΩ)	V_{DGR}	200	150	Vdc
Gate-Source Voltage	V_{GS}	± 20		Vdc
Drain Current Continuous Pulsed	 I_D I_{DM}	 2.2 9.0	 1.8 7.5	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	15 0.12		Watts W/°C
Operating and Storage Temperature Range	T_J, T_{stg}	− 55 to 150		°C

THERMAL CHARACTERISTICS

Rating	Symbol	IRFF210	IRFF213	Unit
Thermal Resistance Junction to Case	$R_{\theta JC}$	8.33		°C/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	175		°C/W
Maximum Lead Temperature 1.6 mm from Case for 10 s	T_L	300		°C

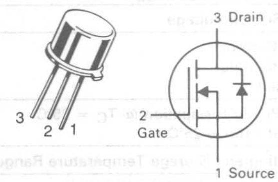
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic			Symbol	Min	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 250 μA)		IRFF210 IRFF213	$V_{(BR)DSS}$	200 150	— —	Vdc
Zero Gate Voltage Drain Current (V_{DS} = Rated V_{DSS}, V_{GS} = 0)			I_{DSS}	—	250	μAdc
Gate-Body Leakage Current, Forward (V_{GS} = 20 Vdc, V_{DS} = 0)			I_{GSSF}	—	100	nAdc
Gate-Body Leakage Current, Reverse (V_{GS} = −20 Vdc, V_{DS} = 0)			I_{GSSR}	—	− 100	nAdc
ON CHARACTERISTICS*						
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μA)			$V_{GS(th)}$	2.0	4.0	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 1.25 A)		IRFF210 IRFF213	$r_{DS(on)}$	— —	1.5 2.4	Ohm
Forward Transconductance (I_D = 1.25 A, V_{DS} = 5.0 V)			g_{fs}	0.8	—	mhos
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	150	pF
Output Capacitance			C_{oss}	—	80	
Reverse Transfer Capacitance			C_{rss}	—	25	
SWITCHING CHARACTERISTICS*						
Turn-On Delay Time	(V_{DD} = 0.5 Rated V_{DSS}, I_D = 1.25 A, R_{gen} = 50 ohms)		$t_{d(on)}$	—	15	ns
Rise Time			t_r	—	25	
Turn-Off Delay Time			$t_{d(off)}$	—	15	
Fall Time			t_f	—	15	
SOURCE-DRAIN DIODE CHARACTERISTICS*						
Forward On-Voltage	(I_S = Rated $I_{D(on)}$, V_{GS} = 0)	IRFF210	V_{SD}	—	2.0	Vdc
		IRFF213	V_{SD}	—	1.8	Vdc
Forward Turn-On Time			t_{on}	—	Negligible	ns
Reverse Recovery Time			t_{rr}	—	200 (Typ)	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

IRFF220
IRFF223

CASE 79-03, STYLE 6
TO-39 (TO-205AF)



TMOS FET
TRANSISTOR

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	IRFF220	IRFF223	Unit
Drain-Source Voltage	V_{DSS}	200	150	Vdc
Drain-Gate Voltage (R_{GS} = 1.0 mΩ)	V_{DGR}	200	150	Vdc
Gate-Source Voltage	V_{GS}	±20		Vdc
Drain Current Continuous Pulsed	 I_D I_{DM}	 3.5 14	 3.0 12	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	20 0.16		Watts W/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150		°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Case	$R_{\theta JC}$	6.25	°C/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	175	°C/W
Maximum Lead Temperature 1.6 mm from Case for 10 s	T_L	300	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

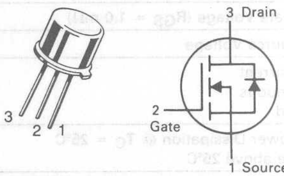
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 250 μA)	IRFF220 IRFF223	$V_{(BR)DSS}$	200 150	—	Vdc
Zero Gate Voltage Drain Current (V_{DS} = Rated V_{DSS}, V_{GS} = 0)		I_{DSS}		250	μAdc
Gate-Body Leakage Current, Forward (V_{GS} = 20 Vdc, V_{DS} = 0)		I_{GSSF}	—	100	nAdc
Gate-Body Leakage Current, Reverse (V_{GS} = −20 Vdc, V_{DS} = 0)		I_{GSSR}	—	−100	nAdc
ON CHARACTERISTICS*					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μA)		$V_{GS(th)}$	2.0	4.0	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 2.0 Adc)	IRFF220 IRFF223	$r_{DS(on)}$	 —	0.8 1.2	Ohm
On-State Drain Current (V_{GS} = 10 Vdc, V_{DS} = 5.0 Vdc)	IRFF220 IRFF223	$I_{D(on)}$	3.5 3.0	 —	A
Forward Transconductance (I_D = 2.0 A, V_{DS} = 5.0 V)		g_{fs}	1.5	—	mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	600	pF
Output Capacitance		C_{oss}	—	300	
Reverse Transfer Capacitance		C_{rss}	—	80	
SWITCHING CHARACTERISTICS*					
Turn-On Delay Time	(V_{DD} = 0.5 Rated $V_{(BR)DSS}$, I_D = 2.0 A, R_{gen} = 50 ohms)	$t_{d(on)}$	—	40	ns
Rise Time		t_r	—	60	
Turn-Off Delay Time		$t_{d(off)}$	—	100	
Fall Time		t_f	—	60	
SOURCE-DRAIN DIODE CHARACTERISTICS*					
Forward On-Voltage	IRFF220	V_{SD}	—	2.0	Vdc
	IRFF223	V_{SD}	—	1.8	Vdc
Forward Turn-On Time	(I_S = Rated $I_{D(on)}$, V_{GS} = 0)	t_{on}	—	Negligible	ns
Reverse Recovery Time		t_{rr}	—	350 (Typ)	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

6

IRFF230
IRFF233

CASE 79-03
TO-39 (TO-205AF)



TMOS FET
TRANSISTOR
N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	IRFF230	IRFF233	Unit
Drain-Source Voltage	V_{DSS}	200	150	Vdc
Drain-Gate Voltage (R_{GS} = 1.0 mΩ)	V_{DGR}	200	150	Vdc
Gate-Source Voltage	V_{GS}	±20		Vdc
Drain Current Continuous Pulsed	 I_D I_{DM}	 5.5 22	 4.5 18	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	25 0.2		Watts W/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150		°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Case	$R_{\theta JC}$	5.0	°C/W
Maximum Lead Temperature 1.6 mm from Case for 10 s	T_L	300	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 250 μA)	IRFF230 IRFF233	$V_{(BR)DSS}$	200 150	— —	Vdc
Zero Gate Voltage Drain Current (V_{DS} = Rated V_{DSS}, V_{GS} = 0)		I_{DSS}	—	250	μAdc
Gate-Body Leakage Current, Forward (V_{GS} = 20 Vdc, V_{DS} = 0)		I_{GSSF}	—	100	nAdc
Gate-Body Leakage Current, Reverse (V_{GS} = −20 Vdc, V_{DS} = 0)		I_{GSSR}	—	−100	nAdc
ON CHARACTERISTICS*					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μA)		$V_{GS(th)}$	2.0	4.0	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 3.0 A)	IRFF230 IRFF233	$r_{DS(on)}$	— —	0.4 0.6	Ohm
Forward Transconductance (I_D = 3.0 A, V_{DS} = 5.0 V)		g_{fs}	2.5	—	mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	800	pF
Output Capacitance		C_{oss}	—	450	
Reverse Transfer Capacitance		C_{rss}	—	150	
SWITCHING CHARACTERISTICS*					
Turn-On Delay Time	(V_{DD} ≈ 90 V, I_D = 3.0 A, R_{gen} = 50 ohms)	$t_{d(on)}$	—	30	ns
Rise Time		t_r	—	50	
Turn-Off Delay Time		$t_{d(off)}$	—	50	
Fall Time		t_f	—	40	
SOURCE-DRAIN DIODE CHARACTERISTICS*					
Forward On-Voltage	IRFF230	V_{SD}	—	2.0	Vdc
	IRFF233	V_{SD}	—	1.8	Vdc
Forward Turn-On Time	(I_S = Rated $I_{D(on)}$, V_{GS} = 0)	t_{on}	—	Negligible	ns
Reverse Recovery Time		t_{rr}	—	450 (Typ)	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

6

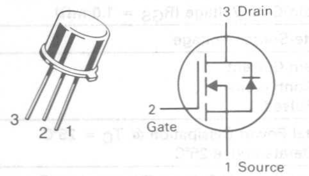
MAXIMUM RATINGS

Rating	Symbol	IRFF330	IRFF333	Unit
Drain-Source Voltage	V_{DSS}	400	350	Vdc
Drain-Gate Voltage (R_{GS} = 1.0 mΩ)	V_{DGR}	400	350	Vdc
Gate-Source Voltage	V_{GS}	±20		Vdc
Drain Current Continuous Pulsed	 I_D I_{DM}	 3.5 14	 3.0 12	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	25 0.2		Watts W/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150		°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Case	$R_{\theta JC}$	5.0	°C/W
Maximum Lead Temperature 1.6 mm from Case for 10 s	T_L	300	°C

CASE 79-03
TO-39 (TO-205AF)



TMOS FET
TRANSISTOR

N-CHANNEL — ENHANCEMENT

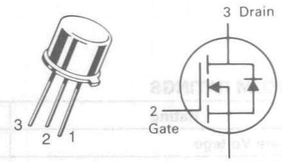
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 250 μA)	IRFF330 IRFF333	$V_{(BR)DSS}$	400 350	— —	Vdc
Zero Gate Voltage Drain Current (V_{DS} = Rated V_{DSS}, V_{GS} = 0)		I_{DSS}	—	250	μAdc
Gate-Body Leakage Current, Forward (V_{GS} = 20 Vdc, V_{DS} = 0)		I_{GSSF}	—	100	nAdc
Gate-Body Leakage Current, Reverse (V_{GS} = −20 Vdc, V_{DS} = 0)		I_{GSSR}	—	100	nAdc
ON CHARACTERISTICS*					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μA)		$V_{GS(th)}$	2.0	4.0	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 2.0 Adc)	IRFF330 IRFF333	$r_{DS(on)}$	— —	1.0 1.5	Ohm
On-State Drain Current (V_{GS} = 10 V, V_{DS} = 5.0 V)	IRFF330 IRFF333	$I_{D(on)}$	3.5 3.0	— —	A
Forward Transconductance (I_D = 2.0 A, V_{DS} = 5.0 V)		g_{fs}	2.0	—	mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	900	pF
Output Capacitance		C_{oss}	—	300	
Reverse Transfer Capacitance		C_{rss}	—	80	
SWITCHING CHARACTERISTICS*					
Turn-On Delay Time	(V_{DD} = 175 V, I_D = 2.0 A, R_{gen} = 50 ohms)	$t_{d(on)}$	—	30	ns
Rise Time		t_r	—	35	
Turn-Off Delay Time		$t_{d(off)}$	—	55	
Fall Time		t_f	—	35	
SOURCE-DRAIN DIODE CHARACTERISTICS*					
Forward On-Voltage	IRFF330	V_{SD}	—	1.6	Vdc
	IRFF333	V_{SD}	—	1.5	Vdc
Forward Turn-On Time	(I_S = Rated $I_{D(on)}$, V_{GS} = 0)	t_{on}		Negligible	ns
Reverse Recovery Time		t_{rr}	—	600 (Typ)	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

IRFF430
IRFF433

CASE 79-03
TO-39 (TO-205AF)



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

6

MAXIMUM RATINGS

Rating	Symbol	IRFF430	IRFF433	Unit
Drain-Source Voltage	V_{DSS}	500	450	Vdc
Drain-Gate Voltage (R_{GS} = 1.0 mΩ)	V_{DGR}	500	450	Vdc
Gate-Source Voltage	V_{GS}	±20		Vdc
Drain Current Continuous Pulsed	 I_D I_{DM}	 2.75 11	 2.25 9.0	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	25 0.2		Watts W/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150		°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Case	$R_{\theta JC}$	5.0	°C/W
Maximum Lead Temperature 1.6 mm from Case for 10 s	T_L	300	°C

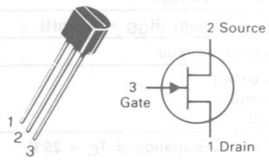
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 250 μA)	IRFF430 IRFF433	$V_{(BR)DSS}$	500 450	— —	Vdc
Zero Gate Voltage Drain Current (V_{DS} = Rated V_{DSS}, V_{GS} = 0)		I_{DSS}	—	250	μAdc
Gate-Body Leakage Current, Forward (V_{GS} = 20 Vdc, V_{DS} = 0)		I_{GSSF}	—	100	nAdc
Gate-Body Leakage Current, Reverse (V_{GS} = −20 Vdc, V_{DS} = 0)		I_{GSSR}	—	−100	nAdc
ON CHARACTERISTICS*					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μA)		$V_{GS(th)}$	2.0	4.0	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 1.5 Adc)	IRFF430 IRFF433	$r_{DS(on)}$	— —	1.5 2.0	Ohm
On-State Drain Current (V_{GS} = 10 Vdc, V_{DS} = 5.0 V)	IRFF430 IRFF433	$I_{D(on)}$	2.75 2.25	— —	A
Forward Transconductance (V_{DS} = 5.0 Vdc, I_D = 1.5 A)		g_{fs}	1.5	—	mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	800	pF
Output Capacitance		C_{oss}	—	200	
Reverse Transfer Capacitance		C_{rss}	—	60	
SWITCHING CHARACTERISTICS*					
Turn-On Delay Time	(V_{DD} = 225 V, I_D = 1.5 A, R_{gen} = 50 ohms)	$t_{d(on)}$	—	30	ns
Rise Time		t_r	—	30	
Turn-Off Delay Time		$t_{d(off)}$	—	55	
Fall Time		t_f	—	30	
SOURCE-DRAIN DIODE CHARACTERISTICS*					
Forward On-Voltage	IRFF430	V_{SD}	—	1.4	Vdc
	IRFF433	V_{SD}	—	1.3	Vdc
Forward Turn-On Time	(I_S = Rated $I_{D(on)}$, V_{GS} = 0)	t_{on}	—	Negligible	ns
Reverse Recovery Time		t_{rr}	—	800 (Typ)	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

J107, J108
J109, J110

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
GENERAL-PURPOSE
TRANSISTOR

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V_{DG}	−25	Vdc
Gate-Source Voltage	V_{GS}	−25	Vdc
Gate Current	I_G	10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	310 2.82	mW mW/°C
Junction Temperature Range	T_J	135	°C
Storage Channel Temperature Range	T_{stg}	−65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Gate-Source Breakdown Voltage (V_{DS} = 0, I_G = −10 μAdc)		$V_{(BR)GSS}$	−25	—	—	Vdc
Gate Reverse Current (V_{GS} = −15 Vdc, V_{DS} = 0) (V_{GS} = −15 Vdc, V_{DS} = 0, T_A = 100°C)		I_{GSS}	— —	— —	−3.0 −200	nAdc
Gate Source Cutoff Voltage (V_{DS} = 15 Vdc, I_D = 10 nAdc)	J107 J108 J109 J110	$V_{GS(off)}$	−0.5 −3.0 −2.0 −0.5	— — — —	−4.5 −10 −6.0 −4.0	Vdc
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current(1) (V_{DS} = 15, V_{GS} = 0)	J107 J108 J109 J110	I_{DSS}	100 80 40 10	— — — —	— — — —	mAdc
Drain-Source On-Resistance (V_{DS} < 0.1 V, V_{GS} = 0 V)	J107 J108 J109 J110	$r_{DS(on)}$	— — — —	— — — —	8.0 8.0 12 18	ohms
SMALL-SIGNAL CHARACTERISTICS						
Drain Gate + Source Gate On-Capacitance (V_{DS} = 0 Vdc, V_{GS} = 0, f = 1.0 MHz)		$C_{dg(on)}$ + $C_{sg(on)}$	—	—	85	pF
Drain Gate Off-Capacitance (V_{DS} = 0 Vdc, V_{GS} = −10 V, f = 1.0 MHz)		$C_{dg(off)}$	—	—	15	pF
Source Gate Off-Capacitance (V_{DS} = 0 Vdc, V_{GS} = −10 V, f = 1.0 MHz)		$C_{sg(off)}$	—	—	15	pF

(1) Pulse Duration 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — COMMON SOURCE INPUT CAPACITANCE versus GATE-SOURCE VOLTAGE

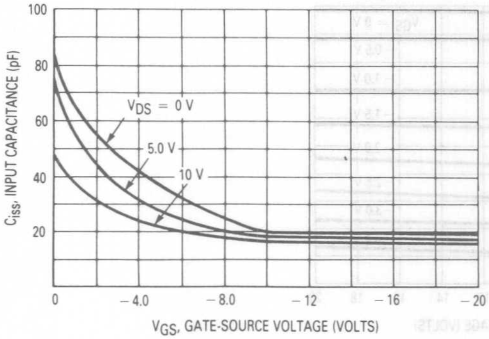


FIGURE 2 — COMMON SOURCE REVERSE FEEDBACK CAPACITANCE versus GATE-SOURCE VOLTAGE

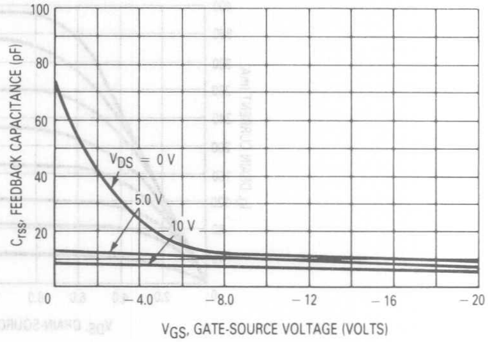


FIGURE 3 — ON-RESISTANCE versus GATE-SOURCE CUTOFF VOLTAGE

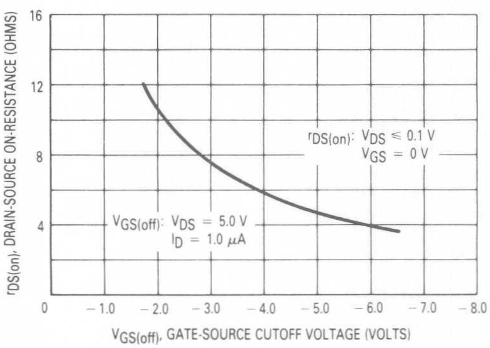


FIGURE 4 — OUTPUT CHARACTERISTIC

$V_{GS(off)} = -2.0$ V

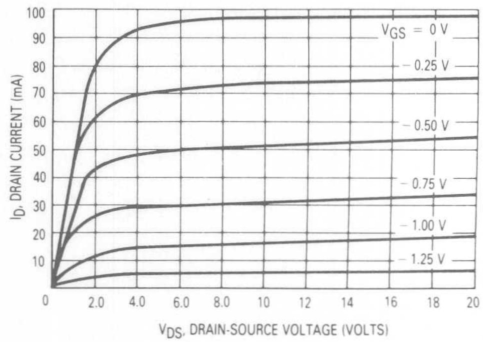


FIGURE 5 — OUTPUT CHARACTERISTIC

$V_{GS(off)} = -3.0$ V

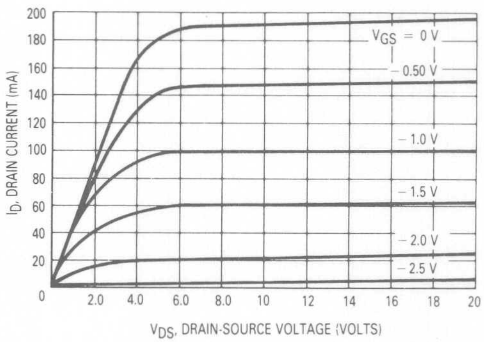
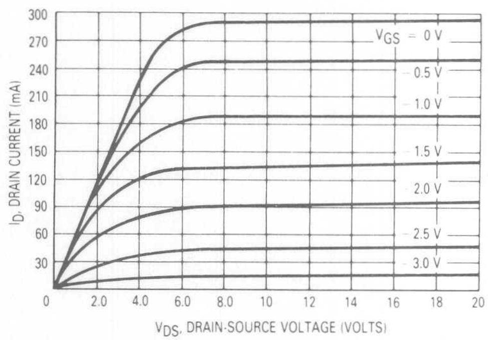


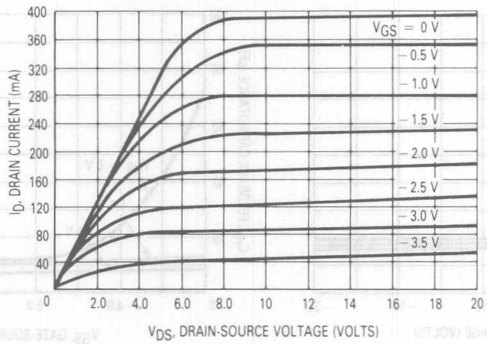
FIGURE 6 — OUTPUT CHARACTERISTIC

$V_{GS(off)} = -4.0$ V



6

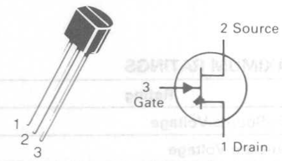
FIGURE 7 — OUTPUT CHARACTERISTIC
$V_{GS(off)} = -5.0$ V



6

J111
J112
J113

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
CHOPPER TRANSISTOR
N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V_{DG}	−35	Vdc
Gate-Source Voltage	V_{GS}	−35	Vdc
Gate Current	I_G	50	mA
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.68	mW mW/°C
Lead Temperature	T_L	300	°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

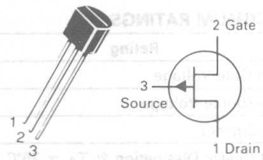
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = −1.0 μA)		$V_{(BR)GSS}$	35	—	Vdc
Gate Reverse Current (V_{GS} = −15 V)		I_{GSS}	—	−1.0	nA
Gate Source Cutoff Voltage (V_{DS} = 5.0 V, I_D = 1.0 μA)	J111 J112 J113	$V_{GS(off)}$	−3.0 −1.0 −0.5	−10 −5.0 −3.0	V
Drain-Cutoff Current (V_{DS} = 5.0 V, V_{GS} = −10 V)		$I_{D(off)}$	—	1.0	nA
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current* (V_{DS} = 15 V)	J111 J112 J113	I_{DSS}	20 5.0 2.0	— — —	mA
Static Drain-Source On Resistance (V_{DS} = 0.1 V)	J111 J112 J113	$r_{DS(on)}$	— — —	30 50 100	Ohms
Drain Gate and Source Gate On-Capacitance (V_{DS} = V_{GS} = 0, f = 1.0 MHz)		$C_{dg(on)}$ + $C_{sg(on)}$	—	28	pF
Drain Gate Off-Capacitance (V_{GS} = −10 V, f = 1.0 MHz)		$C_{dg(off)}$	—	5.0	pF
Source Gate Off-Capacitance (V_{GS} = −10 V, f = 1.0 MHz)		$C_{sg(off)}$	—	5.0	pF

*Pulse Width = 300 μs, Duty Cycle = 3.0%.

J174
J175
J176
J177

CASE 29-04, STYLE 30
TO-92 (TO-226AA)



JFET
CHOPPER TRANSISTOR

P-CHANNEL — DEPLETION

Refer to MPF970 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage	V_{GS}	30	Vdc
Gate Current	I_G	50	mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	350 2.8	mW mW/°C
Storage Temperature Range	T_{stg}	−65 to +150	°C

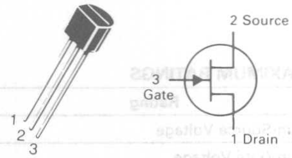
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = 1.0\ \mu A$)		$V_{(BR)GSS}$	30	—	Vdc
Gate Reverse Current ($V_{GS} = 20$ Volts)		I_{GSS}	—	1.0	nA
Gate Source Cutoff Voltage ($V_{DS} = -15$ V, $I_D = -10$ nA)	J174 J175 J176 J177	$V_{GS(off)}$	5.0 3.0 1.0 0.8	10 6.0 4.0 2.5	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current ($V_{DS} = -15$ V)	J174 J175 J176 J177	I_{DSS}*	−2.0 −7.0 −2.0 −1.5	−100 −60 −25 −20	mA
Static Drain-Source On Resistance ($V_{DS} \leq -0.1$ Volt)	J174 J175 J176 J177	$r_{DS(on)}$	— — —	85 125 250 300	Ω

*Pulse Width = 300 μs, Duty Cycle ≤ 3.0%.

J202
J203

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
LOW FREQUENCY/LOW NOISE

N-CHANNEL — DEPLETION

Refer to 2N4220 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	40	Vdc
Drain-Gate Voltage	V_{DG}	40	Vdc
Gate-Source Voltage	V_{GS}	40	Vdc
Gate Current	I_G	50	mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	310 2.82	mW mW/°C
Storage Temperature Range	T_{stg}	−65 to +150	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

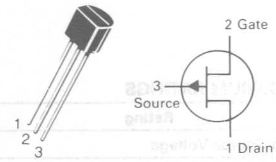
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = -1.0\ \mu A$)		$V_{(BR)GSS}$	−40	—	Vdc
Gate Reverse Current ($V_{GS} = -20$ V)		I_{GSS}	—	−100	pA
Gate Source Cutoff Voltage ($V_{DS} = 20$ V, $I_D = 10$ nA)	J201 J202 J203	$V_{GS(off)}$	−0.3 −0.8 −2.0	−1.5 −4.0 −10.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current ($V_{DS} = 20$ V)	J201 J202 J203	I_{DSS}*	0.2 0.9 4.0	1.0 4.5 20.0	mA
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance ($V_{DS} = 20$ V, f = 1.0 kHz)	J201 J202 J203	$\|y_{fs}\|$*	500 1000 1500	— — —	μmhos

*Pulse Width ≤ 2.0 ms.

6

J270
J271

CASE 29-04, STYLE 30
TO-92 (TO-226AA)



JFET
CHOPPER TRANSISTOR

P-CHANNEL — DEPLETION

Refer to MPF970 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage	V_{GS}	30	Vdc
Gate Current	I_G	50	mA
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	360 3.27	mW mW/°C
Storage Temperature Range	T_{stg}	−65 to +150	°C

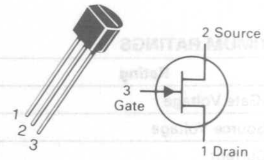
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = 1.0 μA)		$V_{(BR)GSS}$	30	—	Vdc
Gate Reverse Current (V_{GS} = 20 Volts)		I_{GSS}	—	200	pA
Gate Source Cutoff Voltage (V_{DS} = −15 V, I_D = −1.0 nA)	J270 J271	$V_{GS(off)}$	0.5 1.5	2.0 4.5	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current (V_{DS} = −15 V)	J270 J271	I_{DSS}*	−2.0 −6.0	−15 −50	mA
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance (V_{DS} = −15 V, f = 1.0 kHz)	J270 J271	$\|y_{fs}\|$	6000 8000	15000 18000	μmhos
Output Admittance (V_{DS} = −15 V, f = 1.0 kHz)	J270 J271	$\|y_{os}\|$	— —	200 500	μmhos
Input Capacitance (V_{DS} = −15 V, f = 1.0 MHz)		C_{iss}	—	32	pF
Reverse Transfer Capacitance (V_{DS} = −15 V, f = 1.0 MHz)		C_{rss}	—	8.0	pF

*Pulse Width ≤ 2.0 ms.

J300

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
HIGH FREQUENCY AMPLIFIER

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

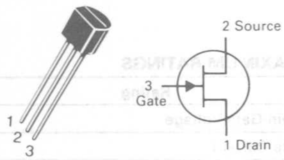
Rating	Symbol	Value	Unit
Drain-Gate Voltage	V_{DG}	−25	Vdc
Gate Current	I_G	10	mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	350 3.5	mW mW/°C
Lead Temperature (1/16″ from Case for 10 Seconds)	T_L	300	°C
Junction Temperature Range	T_J	−55 to +150	°C
Storage Temperature Range	T_{stg}	−55 to +150	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage ($I_G = -1.0\ \mu A$, $V_{DS} = 0$)	$V_{(BR)GSS}$	−25	—	Vdc
Gate Reverse Current ($V_{GS} = -15$ V, $V_{DS} = 0$)	I_{GSS}	—	500	pA
Gate Source Cutoff Voltage ($V_{DS} = 10$ V, $I_D = 1.0$ mA)	$V_{GS(off)}$	−1.0	−6.0	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current ($V_{DS} = 10$ V, $V_{GS} = 0$)	I_{DSS}	6.0	30	mA
Gate-Source Forward Voltage ($V_{DS} = 0$, $I_G = 1.0$ mA)	$V_{GS(f)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance ($V_{DS} = 10$ V, $I_D = 5.0$ mA, f = 1.0 kHz)	$\|y_{fs}\|$	4500	9000	μmhos
Output Admittance ($V_{DS} = 10$ V, $I_D = 5.0$ mA, f = 1.0 kHz)	$\|y_{os}\|$	—	200	μmhos
Input Capacitance ($V_{DS} = 10$ V, $I_D = 5.0$ mA, f = 1.0 MHz)	C_{iss}	—	5.5	pF
Reverse Transfer Capacitance ($V_{DS} = 10$ V, $I_D = 5.0$ mA, f = 1.0 MHz)	C_{rss}	—	1.7	pF

J304
J305

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
HIGH FREQUENCY AMPLIFIER

N-CHANNEL — DEPLETION

6

MAXIMUM RATINGS

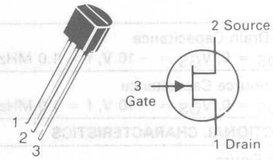
Rating	Symbol	Value	Unit
Drain-Gate Voltage	V_{DG}	−30	Vdc
Gate-Source Voltage	V_{GS}	−30	Vdc
Gate Current	I_G	10	mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	350 3.5	mW mW/°C
Lead Temperature (1/16″ from Case for 10 Seconds)	T_L	300	°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = 1.0\ \mu A$, $V_{DS} = 0$)		$V_{(BR)GSS}$	30	—	Vdc
Gate Reverse Current ($V_{GS} = -20$ V, $V_{DS} = 0$)		I_{GSS}	—	100	pA
Gate Source Cutoff Voltage ($V_{DS} = 15$ V, $I_D = 1.0$ nA)	J304 J305	$V_{GS(off)}$	−2.0 −0.5	−6.0 −3.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current ($V_{DS} = 15$ V, $V_{GS} = 0$)	J304 J305	I_{DSS}	5.0 1.0	15 8.0	mA
SMALL-SIGNAL CHARACTERISTICS					
Output Admittance ($V_{DS} = 15$ V, $V_{GS} = 0$, f = 1.0 kHz)		$\lvert y_{os} \rvert$	—	50	μmhos
Forward Transconductance ($V_{DS} = 15$ V, $V_{GS} = 0$, f = 1.0 kHz)	J304 J305	$Re(y_{fs})$	4500 3000	7500 —	μmhos

J310

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
VHF/UHF AMPLIFIER

N-CHANNEL — DEPLETION

Refer to U308 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Gate-Source Voltage	V_{GS}	25	Vdc
Forward Gate Current	I_{GF}	10	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	350 3.5	mW mW/°C
Junction Temperature Range	T_J	−55 to +125	°C
Storage Temperature Range	T_{stg}	−55 to +150	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Gate-Source Breakdown Voltage ($I_G = -1.0\ \mu A$, $V_{DS} = 0$)		$V_{(BR)GSS}$	−25	—	—	Vdc
Gate Reverse Current ($V_{GS} = -15$ V, $V_{DS} = 0$, $T_A = 25°C$) ($V_{GS} = -15$ V, $V_{DS} = 0$, $T_A = +125°C$)		I_{GSS}	 — —	 — —	 −1.0 −1.0	 nA µA
Gate Source Cutoff Voltage ($V_{DS} = 10$ V, $I_D = 1.0$ nA)	 J308 J309 J310	$V_{GS(off)}$	 −1.0 −1.0 −2.0	 — — —	 −6.5 −4.0 −6.5	Vdc
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current(1) ($V_{DS} = 10$ V, $V_{GS} = 0$)	 J308 J309 J310	I_{DSS}	 12 12 24	 — — —	 60 30 60	mA
Gate-Source Forward Voltage ($V_{DS} = 0$, $I_G = 1.0$ mA)		$V_{GS(f)}$	—	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Common-Source Input Conductance ($V_{DS} = 10$ V, $I_D = 10$ mA, f = 100 MHz)	 J308 J309 J310	$Re(y_{is})$	 — — —	 0.7 0.7 0.5	 — — —	mmhos
Common-Source Output Conductance ($V_{DS} = 10$ V, $I_D = 10$ mA, f = 100 MHz)		$Re(y_{os})$	—	0.25	—	mmhos
Common-Gate Power Gain ($V_{DS} = 10$ V, $I_D = 10$ mA, f = 100 MHz)		G_{pg}	—	16	—	dB
Common-Source Forward Transconductance ($V_{DS} = 10$ V, $I_D = 10$ mA, f = 100 MHz)		$Re(y_{fs})$	—	12	—	mmhos
Common-Gate Input Conductance ($V_{DS} = 10$ V, $I_D = 10$ mA, f = 100 MHz)		$Re(y_{ig})$	—	12	—	mmhos
Common-Gate Forward Transconductance ($V_{DS} = 10$ V, $I_D = 10$ mA, f = 1.0 kHz)	 J308 J309 J310	g_{fs}	 8000 10000 8000	 — — —	 20000 20000 18000	µmhos
Common-Gate Output Conductance ($V_{DS} = 10$ V, $I_D = 10$ mA, f = 1.0 kHz)	 J308 J309 J310	g_{os}	 — — —	 — — —	 200 150 200	µmhos

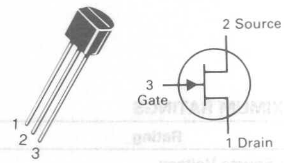
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
Common-Gate Forward Transconductance (V_{DS} = 10 V, I_D = 10 mA, f = 1.0 kHz)	J308 J309 J310	g_{fg}	— — —	13000 13000 12000	— — —	μmhos
Common-Gate Output Conductance (V_{DS} = 10 V, I_D = 10 mA, f = 1.0 kHz)	J308 J309 J310	g_{og}	— — —	150 100 150	— — —	μmhos
Gate-Drain Capacitance (V_{DS} = 0, V_{GS} = −10 V, f = 1.0 MHz)		C_{gd}	—	1.8	2.5	pF
Gate-Source Capacitance (V_{DS} = 0, V_{GS} = −10 V, f = 1.0 MHz)		C_{gs}	—	4.3	5.0	pF
FUNCTIONAL CHARACTERISTICS						
Noise Figure (V_{DS} = 10 V, I_D = 10 mA, f = 450 MHz)		NF	—	1.5	—	dB
Equivalent Short-Circuit Input Noise Voltage (V_{DS} = 10 V, I_D = 10 mA, f = 100 Hz)		$\bar{e}_n$	—	10	—	nV/√Hz

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 3.0%.

JF1033B
JF1033S
JF1033Y

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
HIGH FREQUENCY AMPLIFIER

N-CHANNEL DEPLETION

MAXIMUM RATINGS

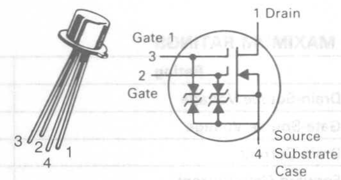
Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	Vdc
Gate-Source Voltage	V_{GS}	25	Vdc
Drain Current	I_D	20	mA
Forward Gate Current	I_{GF}	10	mA
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	310 2.82	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = −10 μA)		$V_{(BR)GSS}$	−25	—	Vdc
Drain-Source Breakdown Voltage (I_D = 10 μA)		$V_{(BR)DGO}$	20	—	Vdc
Gate Reverse Current (V_{GS} = −10 V, V_{DS} = 0)		I_{GSS}	—	−100	nA
Gate Source Cutoff Voltage (V_{DS} = 10 V, I_D = 10 μA)		$V_{GS(off)}$	−1.0	−8.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current (V_{DS} = 10 V, V_{GS} = 0)	JF1033Y JF1033B JF1033S	I_{DSS}	2.5 5.0 10.0	6.0 12.0 20.0	mA
SMALL-SIGNAL CHARACTERISTICS					
Forward Transconductance (V_{DS} = 10 V, V_{GS} = 0, f = 1.0 kHz)		$Re(y_{fs})$	4.5	13.0	mmhos
FUNCTIONAL CHARACTERISTICS					
Noise Figure (V_{DS} = 10 V, V_{GS} = 0, f = 100 MHz)		NF	—	2.5	dB

MFE120
MFE121
MFE122

CASE 20-03, STYLE 9
TO-72 (TO-206AF)



DUAL-GATE MOSFET
VHF AMPLIFIER

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	+25	Vdc
Drain Current	I_D	30	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	300 1.7	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +175	°C

6

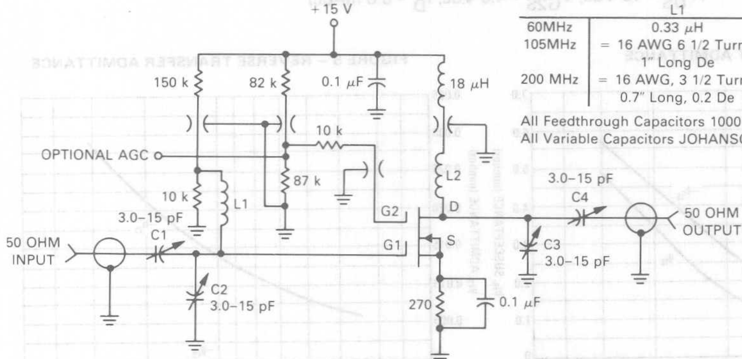
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage ($I_D = 100\ \mu$Adc, $V_S = 0$, $V_{G1S} = -4.0$ V, $V_{G2S} = +4.0$ V)		$V_{(BR)DSX}$	25	—	—	Vdc
Gate 1-Source Breakdown Voltage ($I_{G1} = \pm10\ \mu$Adc, $V_{G2S} = 0$)		$V_{(BR)G1SO}$	±7.0	—	±20	Vdc
Gate 2-Source Breakdown Voltage ($I_{G2} = \pm10\ \mu$Adc, $V_{G2S} = 0$)		$V_{(BR)G2SO}$	±7.0	—	±20	Vdc
Gate 1 Leakage Current ($V_{G1S} = +6.0$ Vdc, $V_{G2S} = 0$, $V_{DS} = 0$)		I_{G1SS}	—	—	20	nAdc
Gate 2 Leakage Current ($V_{G2S} = +6.0$ Vdc, $V_{G1S} = 0$, $V_{DS} = 0$)		I_{G2SS}	—	—	20	nAdc
Gate 1 to Source Cutoff Voltage ($V_{DS} = 15$ Vdc, $V_{G2S} = 4.0$ Vdc, $I_D = 200\ \mu$Adc)		$V_{G1S(off)}$	—	—	−4.0	Vdc
Gate 2 to Source Cutoff Voltage ($V_{DS} = 15$ Vdc, $V_{G1S} = 0$, $I_D = 200\ \mu$Adc)		$V_{G2S(off)}$	—	—	−4.0	Vdc
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current ($V_{DS} = 15$ Vdc, $V_{G1S} = 0$, $V_{G2S} = 4.0$ Vdc)	MFE120 MFE121 MFE122	I_{DSS}	2.0 5.0 2.0	7.0 10 9.0	18 30 20	mAdc
SMALL-SIGNAL CHARACTERISTICS						
Forward Transfer Admittance (Gate 1 to Drain) ($V_{DS} = 15$ Vdc, $V_{G2S} = 4.0$ Vdc, $I_D = 10$ mAdc, f = 1.0 kHz)	MFE120,22 MFE121	$\lvert Y_{fs}\rvert$	8000 10,000	— —	18,000 20,000	μmhos
Input Capacitance ($V_{DS} = 15$ Vdc, $V_{G2S} = 4.0$ Vdc, $I_D = I_{DSS}$, f = 1.0 MHz)	MFE120,22 MFE121	C_{iss}	— —	4.5 4.5	7.0 6.0	pF
Reverse Transfer Capacitance ($V_{DS} = 15$ Vdc, $V_{G2S} = 4.0$ Vdc, $I_D = 6.0$ mAdc, f = 1.0 MHz)		C_{rss}	—	0.023	—	pF
Output Capacitance ($V_{DS} = 15$ Vdc, $V_{G2S} = 4.0$ Vdc, $I_D = I_{DSS}$, f = 1.0 MHz)	MFE120,22 MFE121	C_{oss}	— —	2.5 2.5	4.0 3.5	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
FUNCTIONAL CHARACTERISTICS						
Noise Figure (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 6.0 mAdc, Z_S is optimized for NF) (f = 105 MHz — Figure 1) (f = 60 MHz — Figure 3) (f = 200 MHz — Figure 3)	 MFE120 MFE121 MFE121	NF	 — — —	 2.9 2.6 2.6	 5.0 5.0 5.0	dB
Common Source Power Gain (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 6.0 mAdc, Z_S is optimized for NF) (f = 105 MHz — Figure 1) (f = 60 MHz — Figure 3) (f = 200 MHz — Figure 3)	 MFE120 MFE121 MFE121	G_{ps}	 17 20 17	 19.6 27.8 18.6	 — — —	dB
Level of Unwanted Signal for 1.0% Cross Modulation (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 6.0 mAdc)		—	—	100	—	mV
Common-Source Conversion Power Gain (Gate 1 Injection, Figure 2) (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, Local Oscillator Voltage = 925 mVrms) (Signal Frequency = 60 MHz, Local Oscillator Frequency = 104 MHz) (Signal Frequency = 200 MHz, Local Oscillator Frequency = 244 MHz)	 MFE122 MFE122	G_c	 15 12	 16.5 13.3	 — —	dB

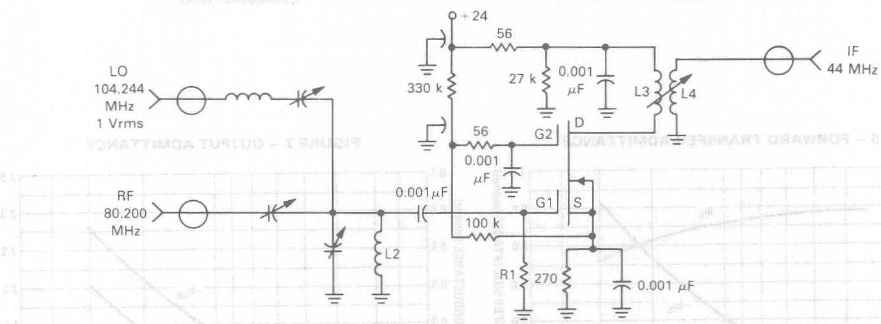
FIGURE 1 — 60, 105 AND 200 MHz POWER GAIN AND NOISE FIGURE TEST CIRCUIT



	L1	L2
60MHz	0.33 μH	0.47 μH
105MHz	= 16 AWG 6 1/2 Turns, 1" Long De	= 16 AWG 5 1/4 Turns, 1" Long, 7/16" De
200 MHz	= 16 AWG, 3 1/2 Turns, 0.7" Long, 0.2 De	= 16 AWG, 4 1/2 Turns, 0.65" Long, 0.2" De

All Feedthrough Capacitors 1000 pf.
All Variable Capacitors JOHANSON JMC2951, 3.0–15 pF

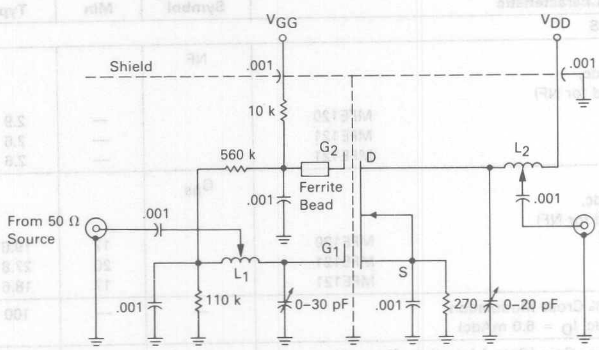
FIGURE 2 — 60 AND 200 MHz CONVERSION GAIN TEST CIRCUIT



	R1	L1	L2	L3	L4
60 MHz	10 k	10 Turns = 22 Enameled on MILLER 4500 4 Core	0.33 μH DELEVAN	15 Turns = 25 Enameled on MILLER 4500 1 Core	4 Turns = 20 Enameled on Sure Core as L3
200 MHz	1.0 k	3 1/2 Turns = 18.1/4" De. 1/2" Long	2 1/2 Turns = 15.3/8" De. 1/2" Long	15 Turns = 26 Enameled on MILLER 4500 1 Core	4 Turns = 26 Enameled on Sure Core as L3

All Feedthrough Capacitors 1000 pf.
All Variable Capacitors JOHANSON JMC2951, 3.0–15 pF

FIGURE 3 – 60 AND 200 MHz CONVERSION POWER GAIN



L_1 2½ T #18, ¼″ diameter center tapped
L_2 3½ T #18, 5/16″ diameter tapped ½T from cold end
C = μF unless otherwise specified

COMMON-SOURCE ADMITTANCE PARAMETERS
(V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 6.0 mAdc)

FIGURE 4 – INPUT ADMITTANCE

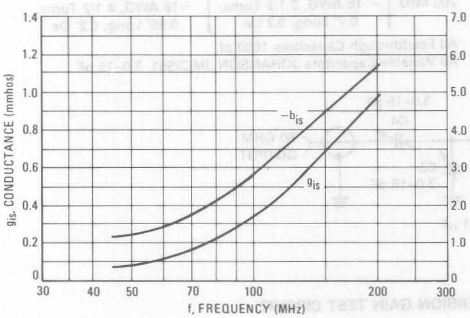


FIGURE 5 – REVERSE TRANSFER ADMITTANCE

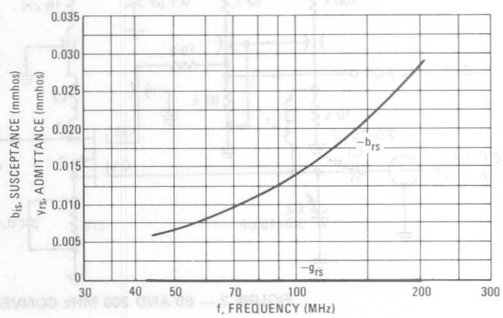


FIGURE 6 – FORWARD TRANSFER ADMITTANCE

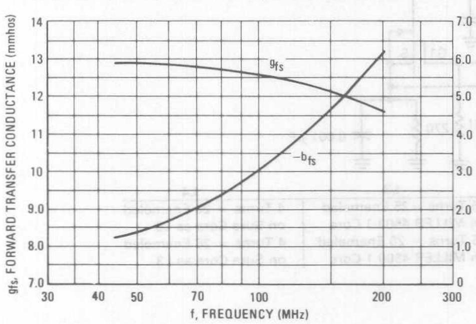
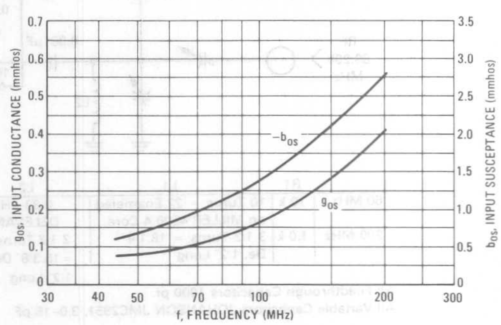
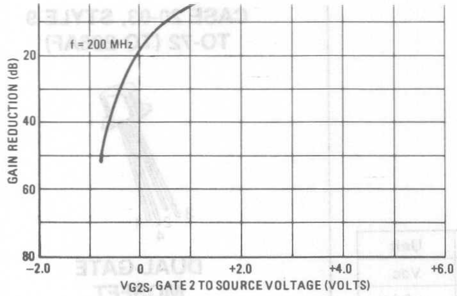
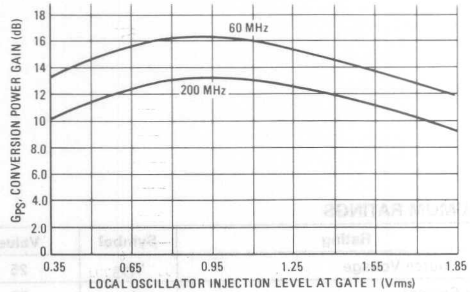


FIGURE 7 – OUTPUT ADMITTANCE




f = 200 MHz
GAIN REDUCTION (dB)
20
40
60
80
−2.0
0
+2.0
+4.0
+6.0
VG2S, GATE 2 TO SOURCE VOLTAGE (VOLTS)


60 MHz
200 MHz
GPS, CONVERSION POWER GAIN (dB)
18
16
14
12
10
8.0
6.0
4.0
2.0
0
0.35
0.65
0.95
1.25
1.55
1.85
LOCAL OSCILLATOR INJECTION LEVEL AT GATE 1 (Vrms)

6

MFE130,131,132

CASE 20-03, STYLE 9
TO-72 (TO-206AF)

DUAL-GATE MOSFET VHF AMPLIFIER

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain Current	I_D	30	mAdc
Total Device Dissipation @ $T_A = 25°C$ (Package Limitation)	P_D	300	mW
Derate above 25°C		1.71	mW/°C
Operating and Storage Channel Temperature Range	$T_{channel}$ T_{stg}	−65 to +175	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage ($I_D = 10\ \mu Adc$, $V_S = 0$, $V_{G1} = -4.0\ V$, $V_{G2} = +4.0\ V$)	$V_{(BR)DSX}$	25	—	—	Vdc
Gate 1-Source Breakdown Voltage ($I_{G1} = \pm 10\ \mu Adc$, $V_{G2S} = 0$)	$V_{(BR)G1SO}$	±7.0	—	±20	Vdc
Gate 2-Source Breakdown Voltage ($I_{G2} = \pm 10\ \mu Adc$, $V_{G2S} = 0$)	$V_{(BR)G2SO}$	±7.0	—	±20	Vdc
Gate 1 Leakage Current ($V_{G1S} = \pm 6.0$ Vdc, $V_{G2S} = 0$, $V_{DS} = 0$)	I_{G1SS}	—	—	20	nAdc
Gate 2 Leakage Current ($V_{G2S} = \pm 6.0$ Vdc, $V_{G1S} = 0$, $V_{DS} = 0$)	I_{G2SS}	—	—	20	nAdc
Gate 1 to Source Cutoff Voltage ($V_{DS} = 15$ Vdc, $V_{G2S} = 4.0$ Vdc, $I_D = 200\ \mu Adc$)	$V_{G1S(off)}$	—	—	−4.0	Vdc
Gate 2 to Source Cutoff Voltage ($V_{DS} = 15$ Vdc, $V_{G1S} = 0$, $I_D = 200\ \mu Adc$)	$V_{G2S(off)}$	—	—	−4.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current ($V_{DS} = 15$ Vdc, $V_{G1S} = 0$, $V_{G2S} = 4.0$ Vdc)	I_{DSS}	3.0	10	30	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance (Gate 1 connected to Drain) ($V_{DS} = 15$ Vdc, $V_{G2S} = 4.0$ Vdc, $I_D = 10$ mAdc, f = 1.0 kHz)	$\|y_{fs}\|$	8000	—	20000	μmhos
Input Capacitance ($V_{DS} = 15$ Vdc $V_{G2S} = 4.0$ Vdc, $I_D = I_{DSS}$, f = 1.0 MHz)	C_{iss}	—	4.5	7.0	pF
Reverse Transfer Capacitance ($V_{DS} = 15$ Vdc, $V_{G2S} = 4.0$ Vdc, $I_D = 6.0$ mAdc, f = 1.0 MHz)	C_{rss}	—	0.023	0.05	pF
Output Capacitance ($V_{DS} = 15$ Vdc, $V_{G2S} = 4.0$ Vdc, $I_D = I_{DSS}$, f = 1.0 MHz)	C_{oss}	—	2.5	4.0	pF
FUNCTIONAL CHARACTERISTICS					
Noise Figure (Figure 7) ($V_{DS} = 15$ Vdc, $V_{G2S} = 4.0$ Vdc, $I_D = 6.0$ mAdc, Z_S is optimized for NF)	NF				dB
(f = 105 MHz) MFE130		—	2.9	5.0	
(f = 60 MHz) MFE131		—	2.5	5.0	
(f = 100 MHz) MFE131		—	3.0	5.0	

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
Common Source Power Gain (Figure 7) (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 6.0 mAdc, Z_S is optimized for NF)		G_{ps}				dB
(f = 105 MHz)	MFE130		17	23	—	
(f = 60 MHz)	MFE131		20	27	—	
(f = 200 MHz)	MFE131		17	20	—	
Level of Unwanted Signal for 1.0% Cross Modulation (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 6.0 mAdc)		—	—	100	—	mV
Common-Source Conversion Power Gain (Gate 1 Injection, Figure 8) (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, Local Oscillator Voltage = 925 mVrms)		G_c				dB
(Signal Frequency = 60 MHz, Local Oscillator Frequency = 104 MHz)	MFE132		15	16.5	—	
(Signal Frequency = 200 MHz, Local Oscillator Frequency = 244 MHz)	MFE132		12	14	—	

COMMON-SOURCE ADMITTANCE PARAMETERS

(V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 6.0 mAdc)

FIGURE 1 – INPUT ADMITTANCE

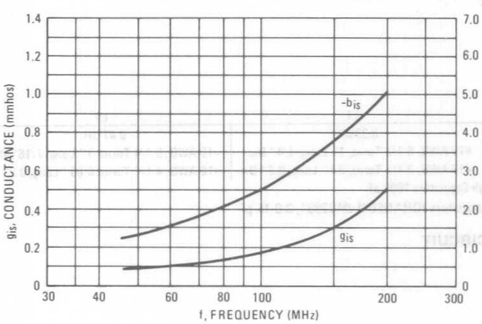


FIGURE 2 – REVERSE TRANSFER ADMITTANCE

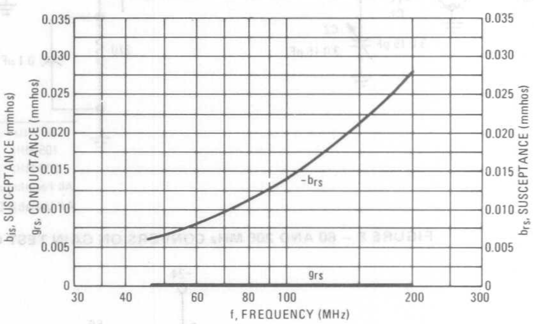


FIGURE 3 – FORWARD TRANSFER ADMITTANCE

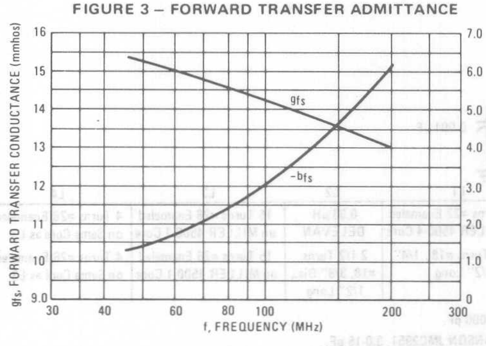


FIGURE 4 – OUTPUT ADMITTANCE

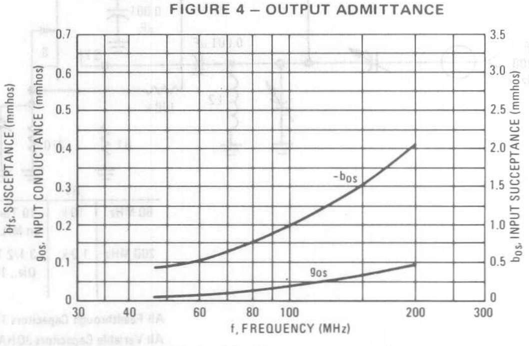


FIGURE 5 – GAIN REDUCTION

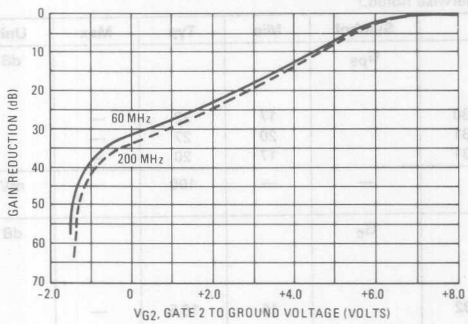


FIGURE 6 – CONVERSION POWER GAIN

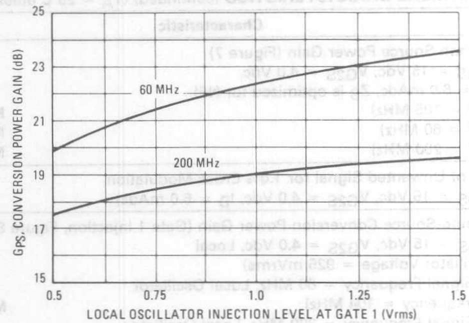
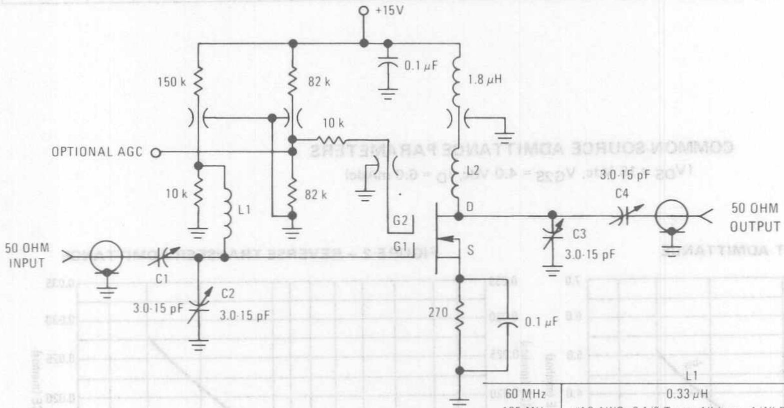


FIGURE 7 – 60, 105 AND 200 MHz POWER GAIN AND NOISE FIGURE TEST CIRCUIT

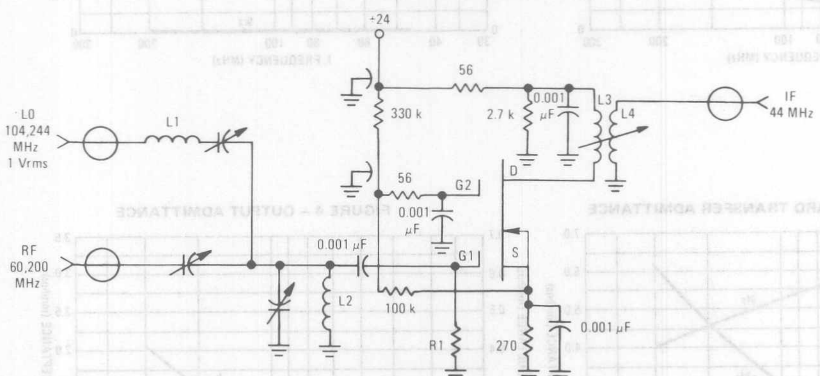


	L1	L2
60 MHz	0.33 µH	0.47 µH
105 MHz	#16 AWG, 6 1/2 Turns, 1" Long, 1/4" Dia.	#16 AWG, 5 1/4 Turns, 1" Long, 7/16" Dia.
200 MHz	#16 AWG, 3 1/2 Turns, 0.7" Long, 0.2" Dia.	#16 AWG, 4 1/2 Turns, 0.65" Long, 0.2" Dia.

All Feedthrough Capacitors 1000 pF

All Variable Capacitors JOHANSON JMC2951, 3.0-15 pF

FIGURE 8 – 60 AND 200 MHz CONVERSION GAIN TEST CIRCUIT



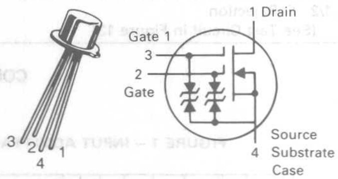
	R1	L1	L2	L3	L4
60 MHz	10 k	10 Turns #22 Enameled on MILLER 4500-4 Core	0.33 µH DELEVAN	15 Turns #26 Enameled on MILLER 4500-1 Core	4 Turns #26 Enameled on Same Core as L3
200 MHz	1.0 k	3 1/2 Turns #18, 1/4" Dia., 1/2" Long	2 1/2 Turns #18, 3/8" Dia., 1/2" Long	15 Turns #26 Enameled on MILLER 4500-1 Core	4 Turns #26 Enameled on Same Core as L3

All Feedthrough Capacitors 1000 pF.

All Variable Capacitors JOHANSON JMC2951, 3.0-15 pF.

MFE140

CASE 20-03, STYLE 9
TO-72 (TO-206AF)



DUAL-GATE MOSFET FM AMPLIFIER

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Gate-Source Voltage	V_{GS}	±7.0	Vdc
Drain Current	I_D	30	mAdc
Gate Current	I_G	10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300	mW
Operating and Storage Channel Temperature Range	$T_{channel}$, T_{stg}	−65 to +175	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (I_D = 10 μAdc, V_S = 0, V_{G1} = −4.0 Vdc, V_{G2} = +4.0 Vdc)	$V_{(BR)DSX}$	25	—	—	Vdc
Gate 1-Source Breakdown Voltage (I_{G1} = ±10 μAdc, V_{G2S} = 0)	$V_{(BR)G1SO}$	±7.0	—	±20	Vdc
Gate 2-Source Breakdown Voltage (I_{G2} = ±10 μAdc, V_{G2S} = 0)	$V_{(BR)G2SO}$	±7.0	—	±20	Vdc
Gate 1 Leakage Current (V_{G1S} = ±6.0 Vdc, V_{G2S} = 0, V_{DS} = 0)	I_{G1SS}	—	—	20	nAdc
Gate 2 Leakage Current (V_{G2S} = ±6.0 Vdc, V_{G1S} = 0, V_{DS} = 0)	I_{G2SS}	—	—	20	nAdc
Gate 1 to Source Cutoff Voltage (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 200 μAdc)	$V_{G1S(off)}$	—	—	−4.0	Vdc
Gate 2 to Source Cutoff Voltage (V_{DS} = 15 Vdc, V_{G1S} = 0, I_D = 200 μAdc)	$V_{G2S(off)}$	—	—	−4.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current (V_{DS} = 15 Vdc, V_{G2S} = 0, V_{G2S} = 4.0 Vdc)	I_{DSS}	3.0	10	30	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance (Gate 1 connected to Drain) (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 10 mAdc, f = 1.0 kHz)	$\|Y_{fs}\|$	10	—	20	mmhos
Input Capacitance (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = I_{DSS}, f = 1.0 MHz)	C_{iss}	—	4.5	7.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = I_{DSS}, = 1.0 MHz)	C_{rss}	—	0.023	0.05	pF
Output Capacitance (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = I_{DSS}, f = 1.0 MHz)	C_{oss}	—	2.5	4.0	pF
FUNCTIONAL CHARACTERISTICS					
Noise Figure (Figure 8) (See Test Circuit in Figure 11)	NF	—	2.5	3.5	dB
Common Source Power Gain (Figure 7) (See Test Circuit in Figure 11)	G_{ps}	20	23	—	dB
Level of Unwanted Signal for 1.0% Cross Modulation (Figure 10) (See Test Circuit in Figure 11)	—	—	45	—	mV

Common-Source Conversion Power Gain (Gate 1 or Gate 2 Injection, Figure 12) (See Test Circuit in Figure 13) (Signal Frequency = 100 MHz, Local Oscillator Frequency = 110.7 MHz)	G_c	15	18.5	—	dB
1/2 I.F. Rejection (See Test Circuit in Figure 13)	1/2 I_{FREJ}	—	50	—	dB

COMMON-SOURCE ADMITTANCE PARAMETERS

(V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 6.0 mAdc)

FIGURE 1 – INPUT ADMITTANCE

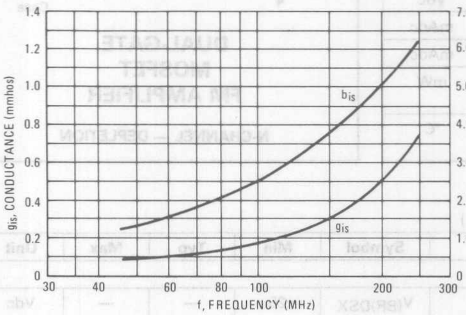


FIGURE 2 – REVERSE TRANSFER ADMITTANCE

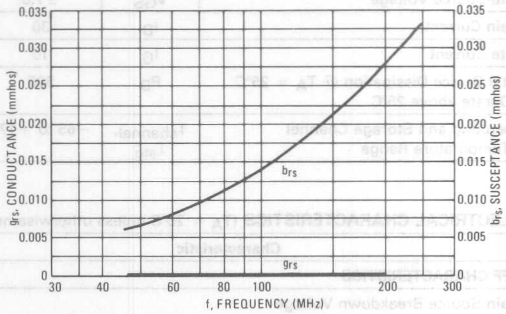


FIGURE 3 – FORWARD TRANSFER ADMITTANCE

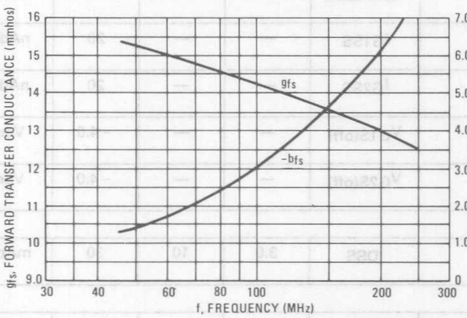
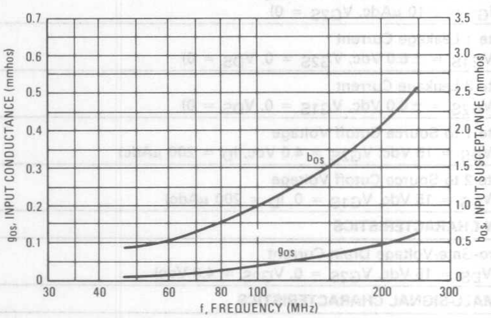


FIGURE 4 – OUTPUT ADMITTANCE



FORWARD TRANSFER ADMITTANCE

(V_{DS} = 15 Vdc, f = 1.0 kHz)

FIGURE 5 – GATE 1

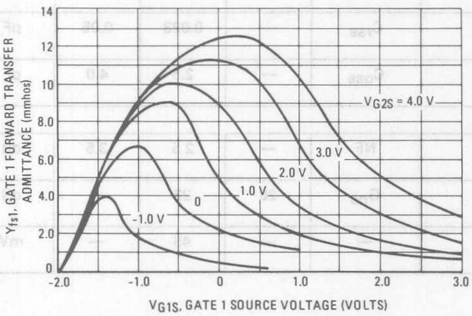
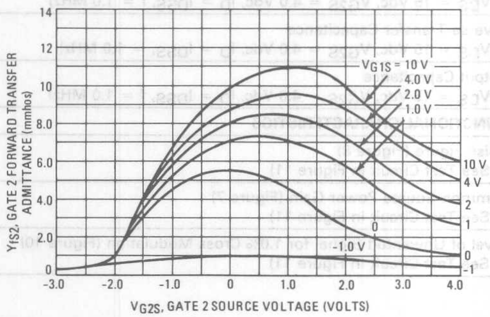
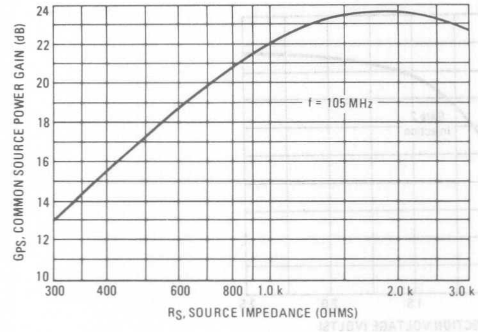


FIGURE 6 – GATE 2





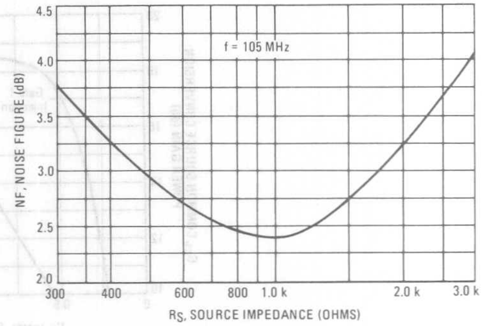


FIGURE 9 – GAIN REDUCTION

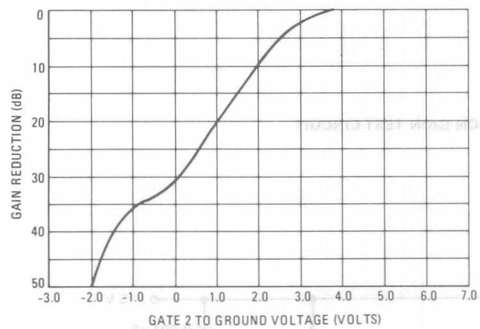


FIGURE 10 – CROSS MODULATION

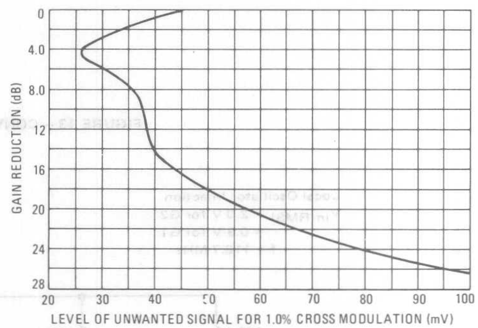
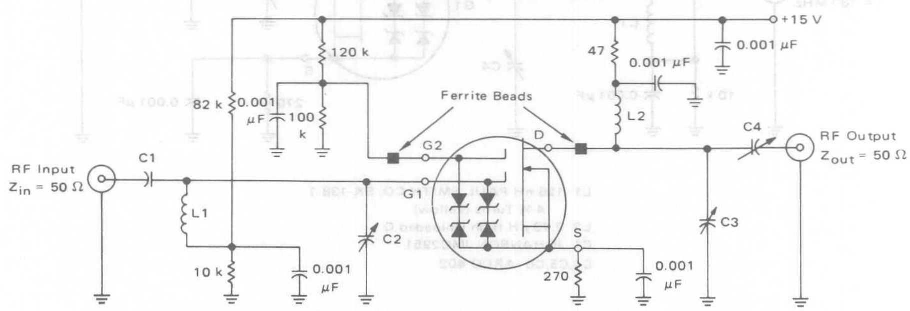


FIGURE 11 – 105 MHz POWER GAIN AND NOISE FIGURE TEST CIRCUIT



The following component values are for a stern stability factor = 2.0.

L1, L2 126 nH PAUL SMITH CO. SK-138-1
4-½ Turns (yellow)

C1 Nominal 7.0 pF Adjusted for source impedance of approximately 1000 Ω, JOHANSON JMC2951

C2 Nominal 4.0 pF ARCO 402

C3 Nominal 13.73 pF ARCO 403

C4 Nominal 4.36 pF JOHANSON JMC2951

All Decoupling Capacitors are Ceramic Discs.

FIGURE 12 – CONVERSION GAIN

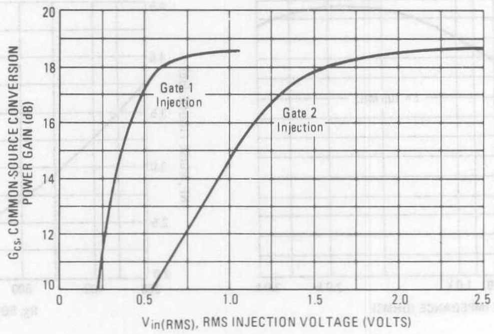
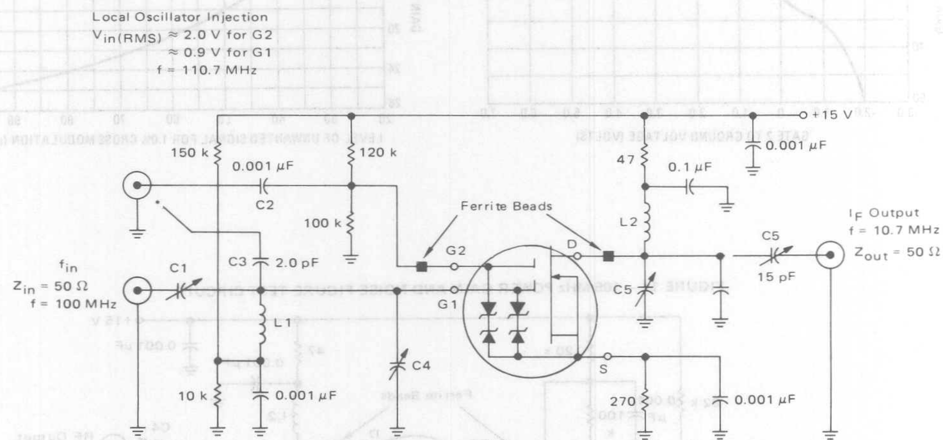


FIGURE 13 – CONVERSION GAIN TEST CIRCUIT



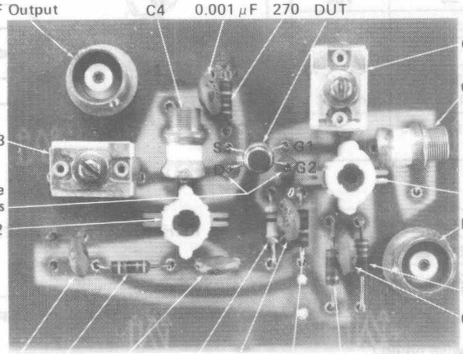
L1 126 nH PAUL SMITH CO. SK-138-1
4-½ Turns (yellow)
L2 2.73 µH High Unloaded Q
C1 JOHANSON JMC2951
C4,C5,C6 ARCO 402

*For G1 injection, C2 is changed to bypass G2 to ground and C3 is added to connect G1 to the injection input.

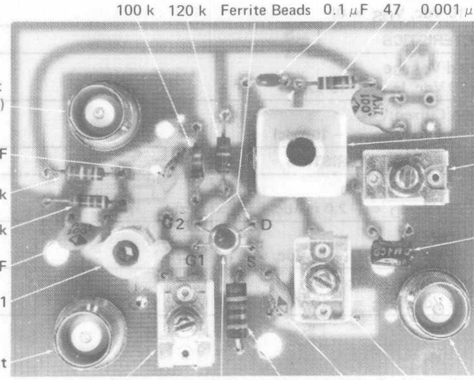
PRINTED CIRCUIT BOARD LAYOUT INFORMATION

FIGURE 14 – TEST FIXTURES

105 MHz POWER GAIN AND NOISE FIGURE TEST CIRCUIT



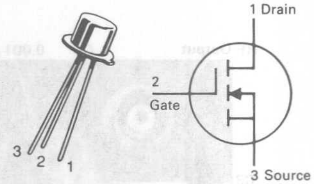
100 MHz to 10.7 MHz CONVERSION GAIN TEST CIRCUIT



Notes:
1. C1 is on the bottom side of the board.
2. For G1 Injection, C2 is changed to bypass G2 to ground and C3 is added to connect G1 to the injection input. See Figure 13.

MFE823

CASE 22-03, STYLE 11
TO-18 (TO-206AA)



MOSFET

P-CHANNEL — ENHANCEMENT

Refer to 2N4352 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG}	±10	Vdc
Drain Current	I_D	30	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 1.71	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +175	°C

THERMAL CHARACTERISTICS

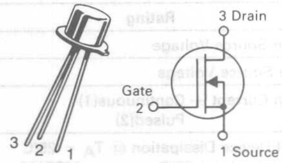
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	584	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	250	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Drain-Source Breakdown Voltage (I_D = −10 μAdc, V_{GS} = 0 Vdc)	$V_{(BR)DSX}$	−25	—	Vdc
Zero-Gate-Voltage Drain Current (V_{DS} = −10 Vdc, V_{GS} = 0)	I_{DSS}	—	−20	nAdc
Gate Reverse Current (V_{GS} = −10 Vdc, V_{DS} = 0)	I_{GSS}	—	1.0	pAdc
ON CHARACTERISTICS				
Gate Threshold Voltage (V_{DS} = −10 Vdc, I_D = −10 μAdc)	$V_{GS(Th)}$	−2.0	−6.0	Vdc
On-State Drain Current (V_{DS} = −10 Vdc, V_{GS} = −10 Vdc)	$I_{D(on)}$	−3.0	—	mAdc
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance (V_{DS} = −10 Vdc, I_D = −2.0 mAdc, f = 1.0 kHz)	$\|y_{fs}\|$	1000	—	μmhos
Input Capacitance (V_{DS} = −10 Vdc, V_{GS} = −10 Vdc, f = 1.0 MHz)	C_{iss}	—	6.0	pF
Reverse Transfer Capacitance (V_{DS} = −10 Vdc, V_{GS} = −10 Vdc, f = 1.0 MHz)	C_{rss}	—	1.5	pF

MFE825

CASE 22-03, STYLE 2
TO-18 (TO-206AA)



MOSFET

N-CHANNEL — DEPLETION

Refer to 2N3796 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	Vdc
Gate-Source Voltage	V_{GS}	30	Vdc
Drain Current	I_D	25	mA
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	200 1.6	mW mW/°C
Junction Temperature Range	T_J	150	°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C

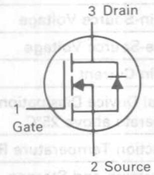
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Drain-Source Breakdown Voltage (I_D = 1.0 μA, V_{GS} = −8.0 V)	$V_{(BR)DSX}$	20	—	Vdc
Gate Reverse Current (V_{GS} = −10 V, V_{DS} = 0 V)	I_{GSS}	—	1.0	pA
Gate Source Voltage (I_D = 1.0 μA, V_{DS} = 2.0 V)	V_{GS}	0	2.0	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current (V_{DS} = 10 V, V_{GS} = 0)	I_{DSS}	1.0	25	mA
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance (V_{DS} = 10 V, V_{GS} = 0, f = 1.0 kHz)	$\lvert y_{fs} \rvert$	500		μmhos

MFE910
MPF910

MFE910
CASE 79-02, STYLE 6
TO-39 (TO-205AD)

MPF910
CASE 29-03, STYLE 22
(TO-226AE)
TO-92



TMOS SWITCHING

N-CHANNEL — ENHANCEMENT

Refer to 2N6659 for additional graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	Vdc
Gate-Source Voltage	V_{GS}	±15	Vdc
Drain Current — Continuous(1) Pulsed(2)	I_D I_{DM}	0.5 1.0	Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C MPF910	P_D	1.0 8.0	Watts mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C MFE910	P_D	6.25 50	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

(1) The Power Dissipation of the package may result in a lower continuous drain current.
(2) Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

6

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Zero-Gate-Voltage Drain Current (V_{DS} = 40 V, V_{GS} = 0)	I_{DSS}	—	0.1	10	μAdc
Gate Reverse Current (V_{GS} = 10 V, V_{DS} = 0)	I_{GSS}	—	0.01	10	nAdc
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 100 μA)	$V_{(BR)DSS}$	60	90	—	Vdc
ON CHARACTERISTICS					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.0 mA)	$V_{GS(th)}$	0.3	1.5	2.5	Vdc
Drain-Source On-Voltage (V_{GS} = 10 V, I_D = 500 mA)	$V_{DS(on)}$	—	—	2.5	Vdc
On-State Drain Current (V_{DS} = 25 V, V_{GS} = 10 V)	$I_{D(on)}$	500	—	—	mA
Forward Transconductance (V_{DS} = 15 V, I_D = 500 mA)	g_{fs}	100	—	—	mmhos

FIGURE 1 — $V_{GS(th)}$ NORMALIZED versus TEMPERATURE

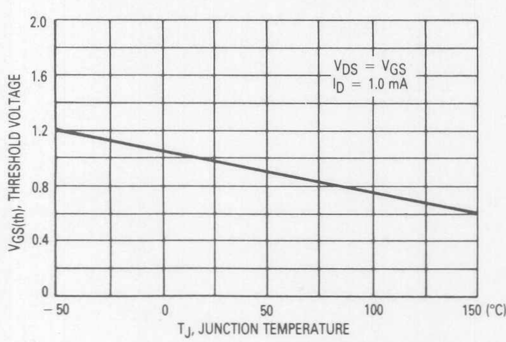


FIGURE 2 — ON-REGION CHARACTERISTICS

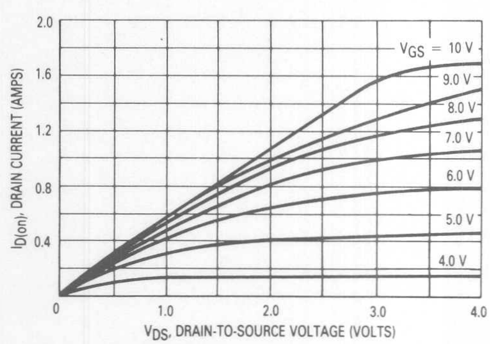


FIGURE 3 — OUTPUT CHARACTERISTICS

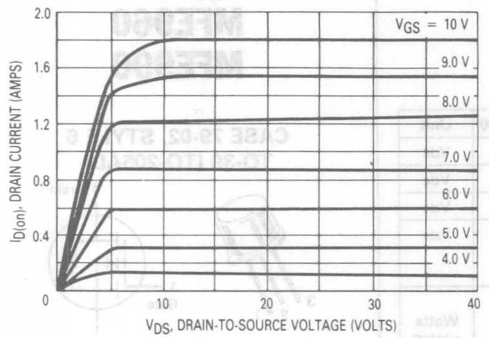
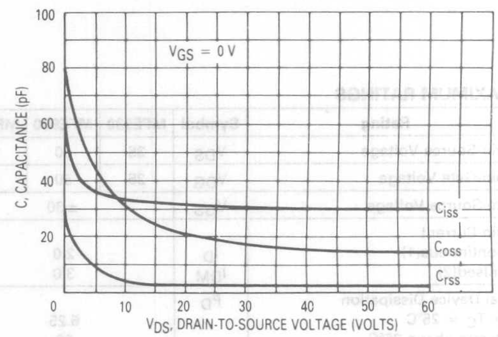


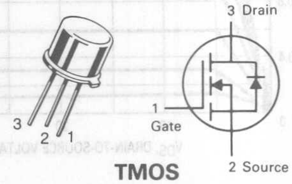
FIGURE 4 — CAPACITANCE versus DRAIN-TO-SOURCE VOLTAGE



6

MFE930
MFE960
MFE990

CASE 79-02, STYLE 6
TO-39 (TO-205AD)



TMOS
SWITCHING

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	MFE930	MFE960	MFE990	Unit
Drain-Source Voltage	V_{DS}	35	60	90	Vdc
Drain-Gate Voltage	V_{DG}	35	60	90	Vdc
Gate-Source Voltage	V_{GS}		±30		Vdc
Drain Current Continuous(1) Pulsed(2)	 I_D I_{DM}		 2.0 3.0		Adc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D		 6.25 50		 Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−55 to 150		°C

(1) The Power Dissipation of the package may result in a lower continuous drain current.
(2) Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

6

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 10 μA)	 MFE930 MFE960 MFE990	$V_{(BR)DSX}$	 35 60 90	 — — —	 — — —	Vdc
Gate Reverse Current (V_{GS} = 15 Vdc, V_{DS} = 0)		I_{GSS}	—	—	50	nAdc
ON CHARACTERISTICS*						
Zero-Gate-Voltage Drain Current (V_{DS} = Maximum Rating, V_{GS} = 0)		I_{DSS}	—	—	10	μAdc
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.0 mA)		$V_{GS(Th)}$	1.0	—	3.5	Vdc
Drain-Source On-Voltage (V_{GS} = 10 V) (I_D = 0.5 A)	 MFE930 MFE960 MFE990	$V_{DS(on)}$	 — — —	 0.4 0.6 0.6	 0.7 0.8 1.2	Vdc
(I_D = 1.0 A)	MFE930 MFE960 MFE990		— — —	0.9 1.2 1.2	1.4 1.7 2.4	
(I_D = 2.0 A)	MFE930 MFE960 MFE990		— — —	2.2 2.8 2.8	3.0 3.5 4.8	
Static Drain-Source On Resistance (V_{GS} = 10 Vdc, I_D = 1.0 Adc)	 MFE930 MFE960 MFE990	$r_{DS(on)}$	 — — —	 0.9 1.2 1.2	 1.4 1.7 2.0	Ohms
On-State Drain Current (V_{DS} = 25 V, V_{GS} = 10 V)		$I_{D(on)}$	1.0	2.0	—	Amps
SMALL-SIGNAL CHARACTERISTICS						
Input Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	60	70	pF
Reverse Transfer Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	—	13	18	pF
Output Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{oss}	—	49	60	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Forward Transconductance (V_{DS} = 25 V, I_D = 0.5 A)	g_{fs}	200	380	—	mmhos
SWITCHING CHARACTERISTICS*					
Turn-On Time (See Figure 1)	t_{on}	—	7.0	15	ns
Turn-Off Time (See Figure 1)	t_{off}	—	7.0	15	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

RESISTIVE SWITCHING

FIGURE 1 — SWITCHING TEST CIRCUIT

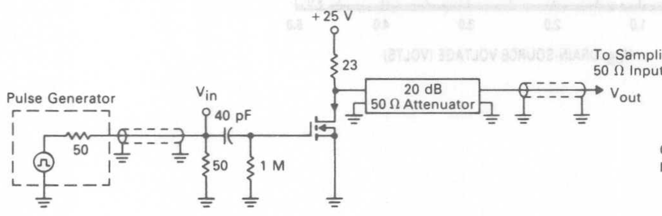


FIGURE 2 — SWITCHING WAVEFORMS

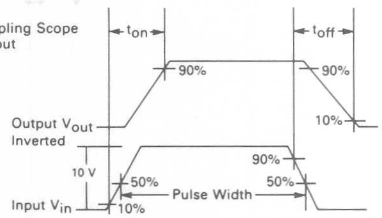


FIGURE 3 — ON VOLTAGE versus TEMPERATURE,

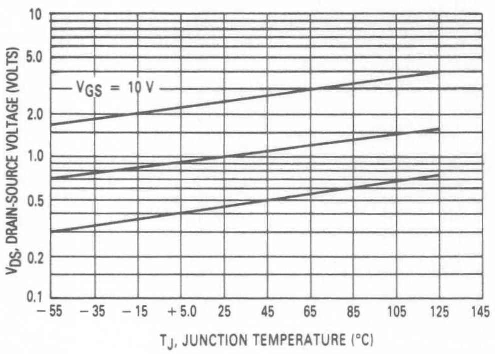


FIGURE 4 — CAPACITANCE VARIATION

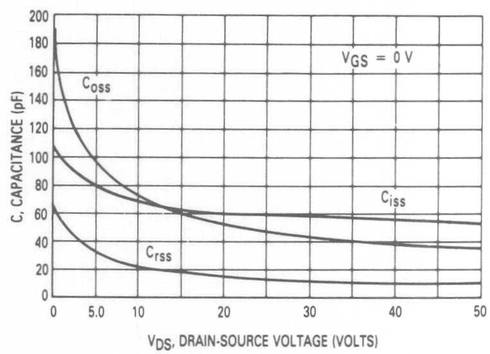


FIGURE 5 — TRANSFER CHARACTERISTIC

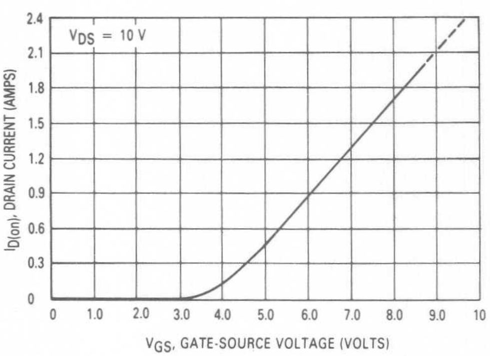
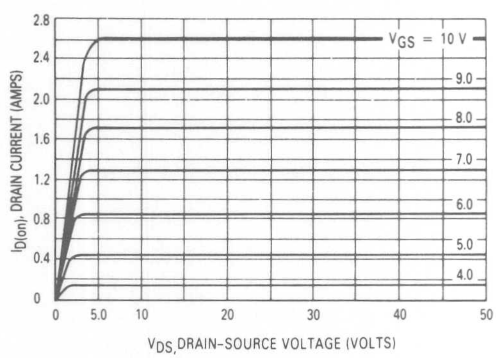
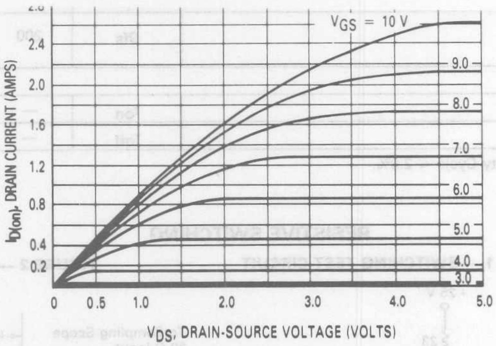


FIGURE 6 — OUTPUT CHARACTERISTIC



6

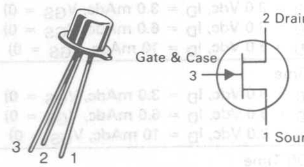


VGS = 10 V
9.0
8.0
7.0
6.0
5.0
4.0
3.0
ID(on), DRAIN CURRENT (AMPS)
2.4
2.0
1.6
1.2
0.8
0.4
0.2
0
0.5
1.0
2.0
3.0
4.0
5.0
VDS, DRAIN-SOURCE VOLTAGE (VOLTS)

6

MFE2004
MFE2005
MFE2006

CASE 22-03, STYLE 4
TO-18 (TO-206AA)



JFET
CHOPPER

N-CHANNEL — DEPLETION

Refer to 2N4091 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage	V_{GS}	30	Vdc
Forward Gate Current	I_{GF}	10	mAdc
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	1.8 10	Watts mW/°C
Junction Temperature Range	T_J	−65 to +175	°C
Storage Temperature Range	T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = 1.0\ \mu Adc$, $V_{DS} = 0$)		$V_{(BR)GSS}$	30	—	Vdc
Gate Reverse Current ($V_{GS} = 20$ Vdc, $V_{DS} = 0$) ($V_{GS} = 20$ Vdc, $V_{DS} = 0$, $T_A = 150°C$)		I_{GSS}	 — —	 0.2 0.4	 nAdc μAdc
Drain Cutoff Current ($V_{DS} = 20$ Vdc, $V_{GS} = 12$ Vdc) ($V_{DS} = 20$ Vdc, $V_{GS} = 12$ Vdc, $T_A = 150°C$)		$I_{D(off)}$	 — —	 0.2 0.4	 nAdc μAdc
Gate Source Voltage ($V_{DS} = 20$ Vdc, $I_D = 50\ \mu Adc$)	 MFE2004 MFE2005 MFE2006	V_{GS}	 1.0 2.0 5.0	 6.0 8.0 10	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current* ($V_{DS} = 20$ Vdc, $V_{GS} = 0$)	 MFE2004 MFE2005 MFE2006	I_{DSS}*	 8.0 15 30	 — — —	mAdc
Gate-Source Forward Voltage ($I_G = 1.0$ mAdc, $V_{DS} = 0$)		$V_{GS(f)}$	—	1.0	Vdc
Drain-Source On-Voltage ($I_D = 3.0$ mAdc, $V_{GS} = 0$) ($I_D = 6.0$ mAdc, $V_{GS} = 0$) ($I_D = 10$ mAdc, $V_{GS} = 0$)	 MFE2004 MFE2005 MFE2006	$V_{DS(on)}$	 — — —	 0.4 0.4 0.4	Vdc
Static Drain-Source On Resistance ($I_D = 1.0$ mAdc, $V_{GS} = 0$)	 MFE2004 MFE2005 MFE2006	$r_{DS(on)}$	 — — —	 80 50 30	Ohms
SMALL-SIGNAL CHARACTERISTICS					
Static Drain-Source "ON" Resistance ($V_{GS} = 0$, $I_D = 0$, f = 1.0 kHz)	 MFE2004 MFE2005 MFE2006	$r_{ds(on)}$	 — — —	 80 50 30	Ohms
Input Capacitance ($V_{DS} = 0$, $V_{GS} = -12$ Vdc, f = 1.0 MHz)		C_{iss}	—	16	pF

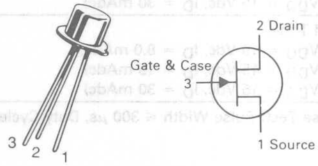
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Reverse Transfer Capacitance		C_{rss}			pF
(V_{DS} = 0, V_{GS} = 6.0 Vdc, f = 1.0 MHz)	MFE2004		—	5.0	
(V_{DS} = 0, V_{GS} = 8.0 Vdc, f = 1.0 MHz)	MFE2005		—	5.0	
(V_{DS} = 0, V_{GS} = 12 Vdc, f = 1.0 MHz)	MFE2006		—	5.0	
SWITCHING CHARACTERISTICS					
Turn-On Delay Time		$t_{d(on)}$			ns
(V_{DD} = 3.0 Vdc, I_D = 3.0 mAdc, V_{GS} = 0)	MFE2004		—	20	
(V_{DD} = 3.0 Vdc, I_D = 6.0 mAdc, V_{GS} = 0)	MFE2005		—	15	
(V_{DD} = 3.0 Vdc, I_D = 10 mAdc, V_{GS} = 0)	MFE2006		—	10	
Rise Time		t_r			ns
(V_{DD} = 3.0 Vdc, I_D = 3.0 mAdc, V_{GS} = 0)	MFE2004		—	40	
(V_{DD} = 3.0 Vdc, I_D = 6.0 mAdc, V_{GS} = 0)	MFE2005		—	20	
(V_{DD} = 3.0 Vdc, I_D = 10 mAdc, V_{GS} = 0)	MFE2006		—	10	
Turn-Off Time		t_{off}			ns
(V_{DD} = 3.0 Vdc, I_D = 3.0 mAdc, $V_{GS(off)}$ = 6.0 Vdc)	MFE2004		—	80	
(V_{DD} = 3.0 Vdc, I_D = 6.0 mAdc, $V_{GS(off)}$ = 8.0 Vdc)	MFE2005		—	60	
(V_{DD} = 3.0 Vdc, I_D = 10 mAdc, $V_{GS(off)}$ = 12 Vdc)	MFE2006		—	40	

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 3.0%.

6

CASE 22-03, STYLE 4
TO-18 (TO-206AA)



JFET
CHOPPER

N-CHANNEL — DEPLETION

Refer to J107 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG}	25	Vdc
Gate-Source Voltage	V_{GS}	25	Vdc
Forward Gate Current	I_{GF}	50	mAdc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.8 10	Watt mW/°C
Junction Temperature Range	T_J	−65 to +175	°C
Storage Temperature Range	T_{stg}	−65 to +200	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = 10 μAdc, V_{DS} = 0)		$V_{(BR)GSS}$	25	—	Vdc
Gate Reverse Current (V_{GS} = 15 Vdc, V_{DS} = 0) (V_{GS} = 15 Vdc, V_{DS} = 0, T_A = 150°C)		I_{GSS}	 — —	 3.0 6.0	 nAdc μAdc
Drain Cutoff Current (V_{DS} = 15 Vdc, V_{GS} = 12 Vdc) (V_{DS} = 15 Vdc, V_{GS} = 12 Vdc, T_A = 150°C)		$I_{D(off)}$	 — —	 3.0 6.0	 nAdc μAdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current* (V_{DS} = 20 Vdc, V_{GS} = 0)	 MFE2010 MFE2011 MFE2012	I_{DSS}*	 15 40 100	 — — —	mAdc
Gate-Source Forward Voltage (I_G = 1.0 mAdc, V_{DS} = 0)		$V_{GS(f)}$	—	1.0	Vdc
Gate-Source Voltage (V_{DS} = 15 Vdc, I_D = 1.0 μAdc)	 MFE2010 MFE2011 MFE2012	V_{GS}	 0.5 1.0 3.0	 10 10 10	Vdc
Drain-Source On-Voltage (I_D = 8.0 mAdc, V_{GS} = 0) (I_D = 15 mAdc, V_{GS} = 0) (I_D = 30 mAdc, V_{GS} = 0)	 MFE2010 MFE2011 MFE2012	$V_{DS(on)}$	 — — —	 0.75 0.75 0.75	Vdc
Static Drain-Source On Resistance (I_D = 1.0 mAdc, V_{GS} = 0)	 MFE2010 MFE2011 MFE2012	$r_{DS(on)}$	 — — —	 25 15 10	Ohms
SMALL-SIGNAL CHARACTERISTICS					
Static Drain-Source "ON" Resistance (V_{GS} = 0, I_D = 0, f = 1.0 kHz)	 MFE2010 MFE2011 MFE2012	$r_{ds(on)}$	 — — —	 25 15 10	Ohms
Input Capacitance (V_{DS} = 0, V_{GS} = 10 Vdc, f = 1.0 MHz)		C_{iss}	—	50	pF
Reverse Transfer Capacitance (V_{DS} = 0, V_{GS} = 12 Vdc, f = 1.0 MHz)		C_{rss}	—	20	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

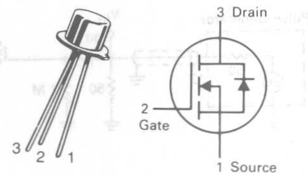
Characteristic		Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS					
Turn-On Delay Time		$t_{d(on)}$	—	10	ns
Rise Time		t_r	—	6.0	ns
Turn-Off Delay Time		$t_{d(off)}$			ns
(V_{DD} = 15 Vdc, I_D = 8.0 mAdc)	MFE2010		—	35	
(V_{DD} = 15 Vdc, I_D = 15 mAdc)	MFE2011		—	20	
(V_{DD} = 15 Vdc, I_D = 30 mAdc)	MFE2012		—	12	
Fall Time		t_f			ns
(V_{DD} = 15 Vdc, I_D = 8.0 mAdc)	MFE2010		—	75	
(V_{DD} = 15 Vdc, I_D = 15 mAdc)	MFE2011		—	45	
(V_{DD} = 15 Vdc, I_D = 30 mAdc)	MFE2012		—	25	

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 3.0%.

6

MFE9200

CASE 22-03, STYLE 12
TO-18 (TO-206AA)



TMOS SWITCHING

N-CHANNEL — ENHANCEMENT

6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	200	Vdc
Gate-Source Voltage	V_{GS}	±20	Vdc
Drain Current Continuous (1) Pulsed (2)	 I_D I_{DM}	 400 800	mAdc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.8 14.4	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 10 μA)	$V_{(BR)DSX}$	200	—	—	Vdc
Gate Reverse Current (V_{GS} = 15 Vdc, V_{DS} = 0)	I_{GSS}	—	0.01	50	nAdc
ON CHARACTERISTICS*					
Zero-Gate-Voltage Drain Current (V_{DS} = 200 V, V_{GS} = 0)	I_{DSS}	—	0.1	10	μAdc
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.0 mA)	$V_{GS(Th)}$	1.0	—	4.0	Vdc
Drain-Source On-Voltage (V_{GS} = 10 V) (I_D = 100 mA) (I_D = 250 mA) (I_D = 500 mA)	$V_{DS(on)}$	 — — —	 0.45 1.20 3.0	 0.6 1.60 —	Vdc
Static Drain-Source On Resistance (V_{GS} = 10 Vdc) (I_D = 100 mA) (I_D = 250 mA) (I_D = 500 mA)	$r_{DS(on)}$	 — — —	 4.5 4.8 6.0	 6.0 6.4 —	Ohms
On-State Drain Current (V_{DS} = 25 V, V_{GS} = 10 V)	$I_{D(on)}$	400	700	—	mA
SMALL-SIGNAL CHARACTERISTICS					
Input Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	—	72	90	pF
Reverse Transfer Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{rss}	—	—	10	pF
Output Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)	C_{oss}	—	—	30	pF
Forward Transconductance (V_{DS} = 25 V, I_D = 250 mA)	g_{fs}	200	400	—	mmhos
SWITCHING CHARACTERISTICS					
Turn-On Time See Figure 1	t_{on}	—	6.0	15	ns
Turn-Off Time See Figure 1	t_{off}	—	6.0	15	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — SWITCHING TEST CIRCUIT

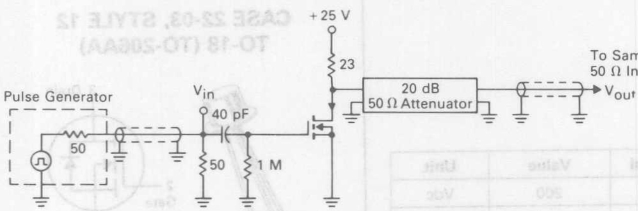
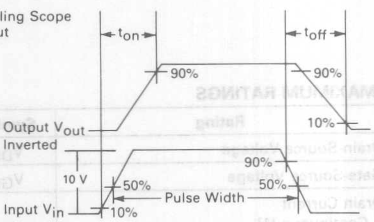


FIGURE 2 — SWITCHING WAVEFORMS



6

FIGURE 3 — ON VOLTAGE versus TEMPERATURE

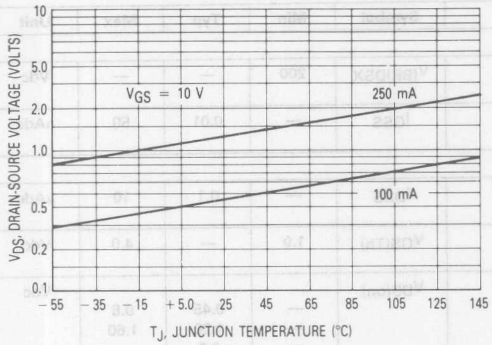


FIGURE 4 — CAPACITANCE VARIATION

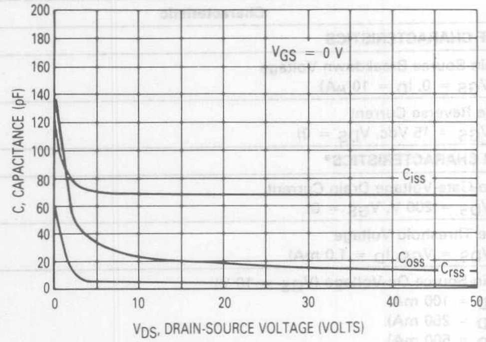


FIGURE 5 — TRANSFER CHARACTERISTIC

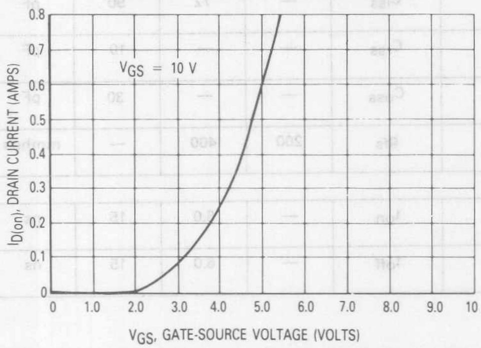
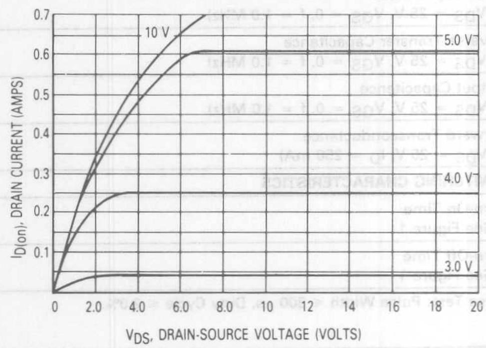
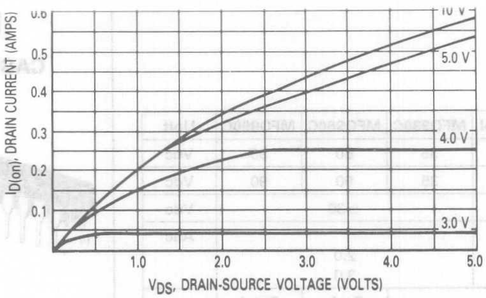


FIGURE 6 — OUTPUT CHARACTERISTIC

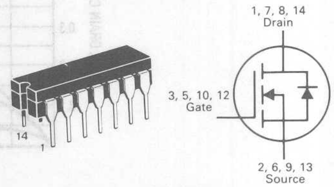



$I_{D(on)}$, DRAIN CURRENT (AMPS)
0.6
0.5
0.4
0.3
0.2
0.1
1.0
2.0
3.0
4.0
5.0
V_{DS}, DRAIN-SOURCE VOLTAGE (VOLTS)
10 V
5.0 V
4.0 V
3.0 V

6

MFQ930C
MFQ960C
MFQ990C

CASE 632-02, STYLE 4
TO-116



QUAD
DUAL-IN-LINE
TMOS

N-CHANNEL — ENHANCEMENT

Refer to MFE930 for graphs.

MAXIMUM RATINGS

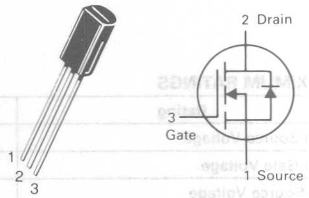
Rating	Symbol	MFQ930C	MFQ960C	MFQ990C	Unit
Drain-Source Voltage	V_{DS}	35	60	90	Vdc
Drain-Gate Voltage	V_{DG}	35	60	90	Vdc
Gate-Source Voltage	V_{GS}		±30		Vdc
Drain Current Continuous (1) Pulsed (2)	 I_D I_{DM}		 2.0 3.0		Adc
			Each Transistor	Total Device	
Total Device Dissipation @ $T_A = 25°C$ Derate Above 25°C	P_D		0.5 17.0	2.0 66.6	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−55 to +150		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage ($V_{GS} = 0$, $I_D = 10\ \mu A$)	 MFQ930C MFQ960C MFQ990C	$V_{(BR)DSX}$	 35 60 90	 — — —	 — — —	Vdc
Gate Reverse Current (V_{GS} = 15 Vdc, V_{DS} = 0)		I_{GSS}	—	—	50	nAdc
ON CHARACTERISTICS*						
Zero-Gate-Voltage Drain Current (V_{DS} = Maximum Rating, V_{GS} = 0)		I_{DSS}	—	—	10	µAdc
Gate Threshold Voltage (I_D = 1.0 mA, $V_{DS} = V_{GS}$)		$V_{GS(Th)}$	1.0	—	3.5	Vdc
Drain-Source On-Voltage (V_{GS} = 10 V) (I_D = 0.5 A)	 MFQ930C MFQ960C MFQ990C	$V_{DS(on)}$	 — — —	 0.4 0.6 0.6	 0.7 0.8 1.0	Vdc
(I_D = 1.0 A)	MFQ930C MFQ960C MFQ990C		— — —	0.9 1.2 1.2	1.4 1.7 2.0	
(I_D = 2.0 A)	MFQ930C MFQ960C MFQ990C		— — —	2.2 2.8 2.8	3.0 3.5 4.0	
Static Drain-Source On Resistance (V_{GS} = 10 Vdc, I_D = 1.0 Adc)	 MFQ930C MFQ960C MFQ990C	$r_{DS(on)}$	 — — —	 0.9 1.2 1.2	 1.4 1.7 2.0	Ohms
On-State Drain Current (V_{DS} = 25 V, V_{GS} = 10 V)		$I_{D(on)}$	1.0	2.0	—	Amps
SMALL-SIGNAL CHARACTERISTICS						
Input Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	60	70	pF
Reverse Transfer Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	—	13	18	pF
Output Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{oss}	—	49	60	pF
Forward Transconductance (V_{DS} = 25 V, I_D = 0.5 A)		g_{fs}	200	380	—	mmhos
SWITCHING CHARACTERISTICS						
Turn-On Time		t_{on}	—	7.0	15	ns
Turn-Off Time		t_{off}	—	7.0	15	ns

MPF89

CASE 29-03, STYLE 7
TO-92 (TO-226AE)



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	200	Vdc
Gate-Source Voltage	V_{GS}	±20	Vdc
Drain Current — Continuous (1) — Pulsed (2)	I_D I_{DM}	400 800	mAdc
Total Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	0.6 4.8	Watts mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150	°C
Thermal Resistance Junction to Ambient	θ_{JA}	208	°C/W

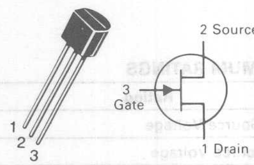
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage ($V_{GS} = 0$, $I_D = 0.5$ mA)	$V_{(BR)DSS}$	200	—	—	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = 200$ V, $V_{GS} = 0$)	I_{DSS}	—	0.1	60	μAdc
Gate-Body Leakage Current ($V_{GS} = 20$ V, $V_{DS} = 0$)	I_{GSS}	—	0.01	100	nAdc
ON CHARACTERISTICS*					
Gate Threshold Voltage ($I_D = 1.0$ mA, $V_{DS} = V_{GS}$)	$V_{GS(th)}$	1.0	—	2.7	Vdc
Drain-Source On-Voltage ($V_{GS} = 10$ V) ($I_D = 100$ mA) ($I_D = 300$ mA) ($I_D = 500$ mA)	$V_{DS(on)}$	 — — —	 0.45 1.2 3.0	 0.6 1.8 	Vdc
On-State Drain Current ($V_{DS} = 25$ V, $V_{GS} = 10$ V)	$I_{D(on)}$	500	700	—	mA
Static Drain-Source On-Resistance ($V_{GS} = 10$ Vdc) ($I_D = 150$ mA) ($I_D = 300$ mA) ($I_D = 500$ mA)	$r_{DS(on)}$	 — — —	 4.5 — 6.0	 6.0 6.0 —	Ohms
Forward Transconductance ($V_{DS} = 25$ V, $I_D = 300$ mA)	g_{fs}	140	400	—	mmhos
DYNAMIC CHARACTERISTICS					
Input Capacitance ($V_{DS} = 25$ V, $V_{GS} = 0$, f = 1.0 MHz)	C_{iss}	—	72	—	pF
Output Capacitance ($V_{DS} = 25$ V, $V_{GS} = 0$, f = 1.0 MHz)	C_{oss}	—	15	—	pF
Reverse Transfer Capacitance ($V_{DS} = 25$ V, $V_{GS} = 0$, f = 1.0 MHz)	C_{rss}	—	2.8	—	pF
SWITCHING CHARACTERISTICS*					
Turn-On Time (See Figure 1)	t_{on}	—	6.0	—	ns
Turn-Off Time (See Figure 1)	t_{off}	—	12	—	ns

(1) The Power Dissipation of the package may result in a lower continuous drain current.
(2) Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MPF102

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
VHF AMPLIFIER

N-CHANNEL — DEPLETION

Refer to 2N4416 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG}	25	Vdc
Gate-Source Voltage	V_{GS}	−25	Vdc
Gate Current	I_G	10	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	200 2	mW mW/°C
Junction Temperature Range	T_J	125	°C
Storage Temperature Range	T_{stg}	−65 to +150	°C

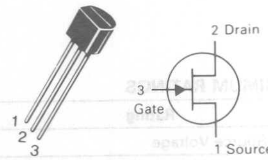
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage ($I_G = -10\ \mu$Adc, $V_{DS} = 0$)	$V_{(BR)GSS}$	−25	—	Vdc
Gate Reverse Current ($V_{GS} = -15$ Vdc, $V_{DS} = 0$) ($V_{GS} = -15$ Vdc, $V_{DS} = 0$, $T_A = 100°C$)	I_{GSS}	 — —	 −2.0 −2.0	 nAdc μAdc
Gate Source Cutoff Voltage ($V_{DS} = 15$ Vdc, $I_D = 2.0$ nAdc)	$V_{GS(off)}$	—	−8.0	Vdc
Gate Source Voltage ($V_{DS} = 15$ Vdc, $I_D = 0.2$ mAdc)	V_{GS}	−0.5	−7.5	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current* ($V_{DS} = 15$ Vdc, $V_{GS} = 0$ Vdc)	I_{DSS}	2.0	20	mAdc
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance* ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 1.0 kHz) ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 100 MHz)	$\|y_{fs}\|$	 2000 1600	 7500 —	μmhos
Input Admittance ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 100 MHz)	$Re(y_{is})$	—	800	μmhos
Output Conductance ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 100 MHz)	$Re(y_{os})$	—	200	μmhos
Input Capacitance ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 1.0 MHz)	C_{iss}	—	7.0	pF
Reverse Transfer Capacitance ($V_{DS} = 15$ Vdc, $V_{GS} = 0$, f = 1.0 MHz)	C_{rss}	—	3.0	pF

*Pulse Test: Pulse Width ≤ 630 ms; Duty Cycle ≤ 10%.

MPF256

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
AMPLIFIER

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	±30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Reverse Gate-Source Voltage	V_{GSR}	30	Vdc
Forward Gate Current	$I_{G(f)}$	10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.73	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

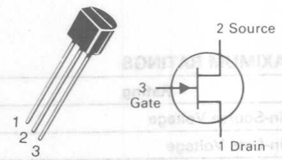
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Gate-Source Breakdown Voltage (I_G = 10 μAdc, V_{DS} = 0)		$V_{(BR)GSS}$	25	—	—	Vdc
Gate Reverse Current (V_{GS} = 15 Vdc, V_{DS} = 0)		I_{GSS}	—	—	5.0	nAdc
Gate Source Cutoff Voltage (V_{DS} = 15 Vdc, I_D = 200 μAdc)		$V_{GS(off)}$	0.5	—	7.5	Vdc
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current (V_{DS} = 15 Vdc, V_{GS} = 0)	Red Green Violet	I_{DSS}*	3.0 6.0 11	— — —	7.0 13 18	mAdc
SMALL-SIGNAL CHARACTERISTICS						
Forward Transfer Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)		$\lvert y_{fs} \rvert$	6.0	—	—	mmhos
Input Capacitance (V_{DS} = 15 Vdc, I_D = 10 mAdc, f = 1.0 MHz)		C_{iss}	—	3.0	—	pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, I_D = 10 mAdc, f = 1.0 MHz)		C_{rss}	—	1.2	—	pF
Output Capacitance (V_{DS} = 15 Vdc, I_D = 10 mAdc, f = 1.0 kHz)		C_{oss}	—	2.0	—	pF
FUNCTIONAL CHARACTERISTICS						
Noise Figure (V_{DS} = 15 Vdc, R_S = 50 Ohms)	100 MHz 400 MHz	NF		— —	2.0 4.0	dB
Common Source Power Gain (V_{DS} = 15 Vdc, R_S = 50 Ohms)	100 MHz 400 MHz	G_{ps}	20 12	— —	— —	dB

*To characterize these devices to narrower limits, the entire production lot is tested and divided into color-coded groups, with each color dot representing an I_{DSS} range.

When packaged for shipment, the colors are randomly selected and no specific color distribution is implied or guaranteed.

MPF820

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
RF AMPLIFIER

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG}	25	Vdc
Reverse Gate-Source Voltage	V_{GSR}	25	Vdc
Forward Gate Current	$I_{G(f)}$	10	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = 10 μAdc, V_{DS} = 0)	$V_{(BR)GSS}$	25	—	—	Vdc
Gate Reverse Current (V_{GS} = 15 Vdc, V_{DS} = 0)	I_{GSS}	—	—	5.0	nAdc
Gate Source Cutoff Voltage (V_{DS} = 15 Vdc, I_D = 200 μAdc)	$V_{GS(off)}$	—	—	5.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain (V_{DS} = 15 Vdc, V_{GS} = 0)	I_{DSS}	10	—	—	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)	$\|y_{fs}\|$	—	20	—	mmhos
Input Capacitance (V_{DS} = 15 Vdc, I_D = 10 mAdc, f = 1.0 MHz)	C_{iss}	—	15		pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, I_D = 10 mAdc, f = 1.0 MHz)	C_{rss}	—	3.5		pF
Common-Gate Input Conductance (V_{DS} = 15 Vdc, I_D = 10 mAdc, f = 100 MHz)	g_{ig}	—	16	—	mmhos
Common-Gate Output Conductance (V_{DS} = 15 Vdc, I_D = 10 mAdc, f = 100 MHz)	G_{og}	—	—	16	μmhos
Common-Gate Forward Transadmittance (V_{DS} = 15 Vdc, I_D = 10 mAdc, f = 100 MHz)	y_{fg}	—	18		mmhos
Common-Gate Reverse Transadmittance (V_{DS} = 15 Vdc, I_D = 10 mAdc, f = 100 MHz)	y_{rg}	—	—	130	μmhos
Output Capacitance (V_{DS} = 15 Vdc, I_D = 10 mAdc, f = 1.0 kHz)	C_{oss}	—	3.5	—	pF
FUNCTIONAL CHARACTERISTICS					
Noise Figure (V_{DS} = 15 Vdc, I_D = 10 mAdc, See Figure 5)	NF			4.0	dB
Small-Signal Power Gain (V_{DS} = 15 Vdc, I_D = 10 mAdc, See Figure 5)	G_{pg}		11	—	dB

6

FIGURE 1 – NOISE FIGURE

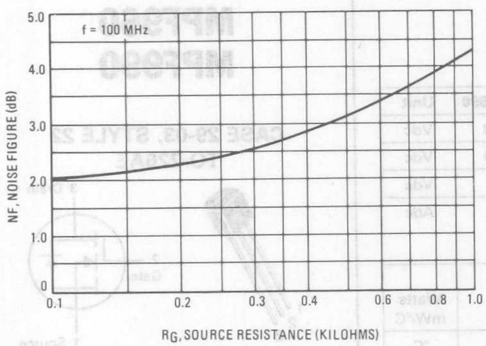


FIGURE 2 – FORWARD TRANSADMITTANCE

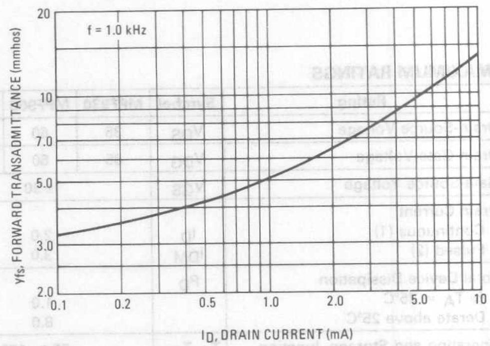


FIGURE 3 – INPUT CAPACITANCE

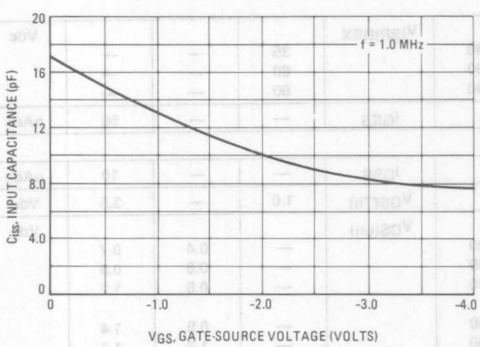


FIGURE 4 – OUTPUT AND REVERSE TRANSFER CAPACITANCE

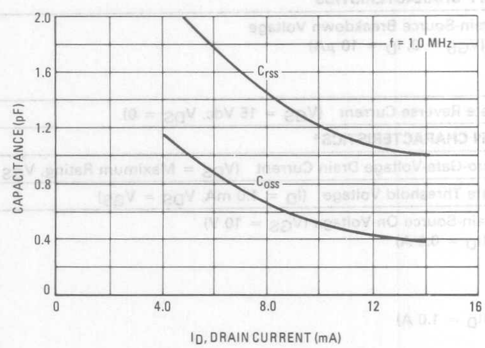
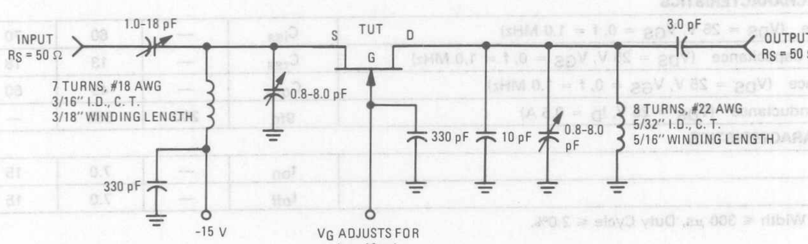


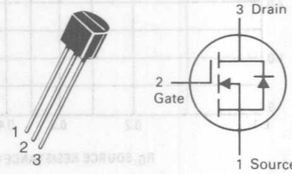
FIGURE 5 – 100 MHz TEST CIRCUIT



MPF910 For Specifications, See MFE910 Data.

MPF930
MPF960
MPF990

CASE 29-03, STYLE 22
TO-226AE



TMOS
SWITCHING

N-CHANNEL — ENHANCEMENT

Refer to MFE930 for graphs.

MAXIMUM RATINGS

Rating	Symbol	MPF930	MPF960	MPF990	Unit
Drain-Source Voltage	V_{DS}	35	60	90	Vdc
Drain-Gate Voltage	V_{DG}	35	60	90	Vdc
Gate-Source Voltage	V_{GS}		±30		Vdc
Drain Current Continuous (1) Pulsed (2)	 I_D I_{DM}		 2.0 3.0		Adc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D		 1.0 8.0		 Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−55 to 150		°C
Thermal Resistance	θ_{JA}		125		°C/W

(1) The Power Dissipation of the package may result in a lower continuous drain current.
(2) Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

6

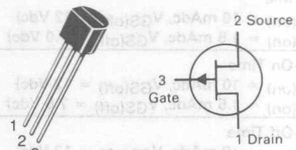
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage ($V_{GS} = 0$, $I_D = 10\ \mu A$)	 MPF930 MPF960 MPF990	$V_{(BR)DSX}$	 35 60 90	 — — —	 — — —	Vdc
Gate Reverse Current (V_{GS} = 15 Vdc, V_{DS} = 0)		I_{GSS}	—	—	50	nAdc
ON CHARACTERISTICS*						
Zero-Gate-Voltage Drain Current (V_{DS} = Maximum Rating, V_{GS} = 0)		I_{DSS}	—	—	10	μAdc
Gate Threshold Voltage (I_D = 1.0 mA, $V_{DS} = V_{GS}$)		$V_{GS(Th)}$	1.0	—	3.5	Vdc
Drain-Source On-Voltage (V_{GS} = 10 V) (I_D = 0.5 A)	 MPF930 MPF960 MPF990	$V_{DS(on)}$	 — — —	 0.4 0.6 0.6	 0.7 0.8 1.2	Vdc
(I_D = 1.0 A)	MPF930 MPF960 MPF990		— — —	0.9 1.2 1.2	1.4 1.7 2.4	
(I_D = 2.0 A)	MPF930 MPF960 MPF990		— — —	2.2 2.8 2.8	3.0 3.5 4.8	
Static Drain-Source On Resistance (V_{GS} = 10 Vdc, I_D = 1.0 Adc)	 MPF930 MPF960 MPF990	$r_{DS(on)}$	 — — —	 0.9 1.2 1.2	 1.4 1.7 2.0	Ohms
On-State Drain Current (V_{DS} = 25 V, V_{GS} = 10 V)		$I_{D(on)}$	1.0	2.0	—	Amps
SMALL-SIGNAL CHARACTERISTICS						
Input Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	60	70	pF
Reverse Transfer Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	—	13	18	pF
Output Capacitance (V_{DS} = 25 V, V_{GS} = 0, f = 1.0 MHz)		C_{oss}	—	49	60	pF
Forward Transconductance (V_{DS} = 25 V, I_D = 0.5 A)		g_{fs}	200	380	—	mmhos
SWITCHING CHARACTERISTICS						
Turn-On Time		t_{on}	—	7.0	15	ns
Turn-Off Time		t_{off}	—	7.0	15	ns

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

MPF970
MPF971

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
SWITCHING

P-CHANNEL — DEPLETION

6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Reverse Gate-Source Voltage	V_{GSR}	30	Vdc
Forward Gate Current	$I_{G(f)}$	10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8	mW mW/°C
Storage Channel Temperature Range	T_{stg}	−65 to +150	°C
Operating Temperature Range	$T_{channel}$	−65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Gate-Source Breakdown Voltage (I_G = 1.0 μAdc, V_{DS} = 0)		$V_{(BR)GSS}$	30	—	—	Vdc
Gate Reverse Current (V_{GS} = 15 Vdc, V_{DS} = 0) (V_{GS} = 15 Vdc, V_{DS} = 0, T_A = 150°C)		I_{GSS}	 — —	 — —	 1.0 1.0	 nAdc μAdc
Drain-Cutoff Current (V_{DS} = 15 Vdc, V_{GS} = 12 Vdc) (V_{DS} = 15 Vdc, V_{GS} = 12 Vdc, T_A = 150°C) (V_{DS} = 15 Vdc, V_{GS} = 7.0 Vdc) (V_{DS} = 15 Vdc, V_{GS} = 7.0 Vdc, T_A = 150°C)	 MPF970 MPF970 MPF971 MPF971	$I_{D(off)}$	 — — — —	 — — — —	 10 10 10 10	 nAdc μAdc nAdc μAdc
Gate Source Cutoff Voltage (V_{DS} = 15 Vdc, I_D = 10 nAdc)	 MPF970 MPF971	$V_{GS(off)}$	 5.0 1.0	 — —	 12 7.0	Vdc
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current(1) (V_{DS} = 20 Vdc, V_{GS} = 0)	 MPF970 MPF971	I_{DSS}	 15 2.0	 — —	 100 50	mAdc
Drain-Source On-Voltage (I_D = 10 mAdc, V_{GS} = 0) (I_D = 1.5 mAdc, V_{GS} = 0)		$V_{DS(on)}$	 — —	 — —	 1.5 1.5	Vdc
Static Drain-Source On Resistance (I_D = 1.0 mAdc, V_{GS} = 0)	 MPF970 MPF971	$r_{DS(on)}$	 — —	 — —	 100 250	Ohms
SMALL-SIGNAL CHARACTERISTICS						
Drain-Source "ON" Resistance (V_{GS} = 0, I_D = 0, f = 1.0 kHz)	 MPF970 MPF971	$r_{ds(on)}$	 — —	 — —	 100 250	Ohms
Input Capacitance (V_{GS} = 12 Vdc, V_{DS} = 0, f = 1.0 MHz) (V_{GS} = 7.0 Vdc, V_{DS} = 0, f = 1.0 MHz)	 MPF970 MPF971	C_{iss}	 — —	 — —	 12 12	pF
Reverse Transfer Capacitance (V_{GS} = 12 Vdc, V_{DS} = 0, f = 1.0 MHz) (V_{GS} = 7.0 Vdc, V_{DS} = 0, f = 1.0 MHz)	 MPF970 MPF971	C_{rss}	 — —	 — —	 5.0 5.0	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS (See Figure 6, R_K = 0) (1)						
Rise Time		t_r				ns
($I_{D(on)}$ = 10 mAdc, $V_{GS(off)}$ = 12 Vdc)	MPF970		—	2.0	5.0	
($I_{D(on)}$ = 1.5 mAdc, $V_{GS(off)}$ = 7.0 Vdc)	MPF971		—	3.0	5.0	
Fall Time		t_f				ns
($I_{D(on)}$ = 10 mAdc, $V_{GS(off)}$ = 12 Vdc)	MPF970		—	9.0	15	
($I_{D(on)}$ = 1.5 mAdc, $V_{GS(off)}$ = 7.0 Vdc)	MPF971		—	68	80	
Turn-On Time		t_{on}				ns
($I_{D(on)}$ = 10 mAdc, $V_{GS(off)}$ = 12 Vdc)	MPF970		—	3.5	8.0	
($I_{D(on)}$ = 1.5 mAdc, $V_{GS(off)}$ = 7.0 Vdc)	MPF971		—	5.0	10	
Turn-Off Time		t_{off}				ns
($I_{D(on)}$ = 10 mAdc, $V_{GS(off)}$ = 12 Vdc)	MPF970		—	13	25	
($I_{D(on)}$ = 1.5 mAdc, $V_{GS(off)}$ = 7.0 Vdc)	MPF971		—	88	120	

(1) Pulse Test: Pulse Width ≤ 100 μs, Duty Cycle ≤ 1.0%.

FIGURE 1 — EFFECT OF I_{DSS} ON DRAIN-SOURCE RESISTANCE AND GATE-SOURCE VOLTAGE

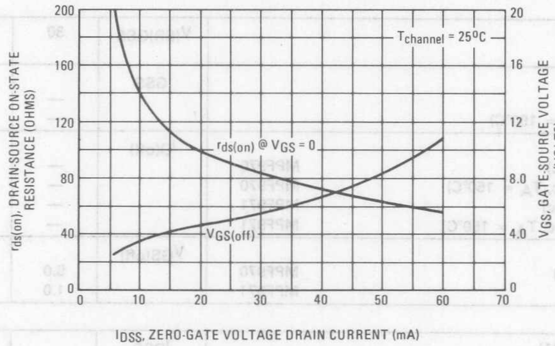


FIGURE 2 — TURN-ON DELAY TIME

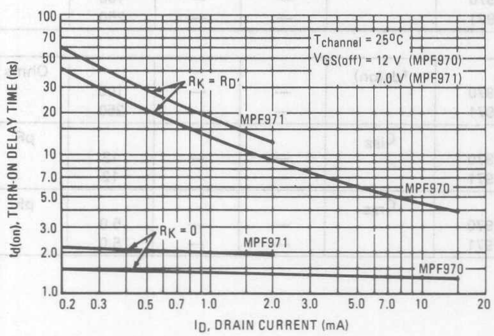


FIGURE 3 — RISE TIME

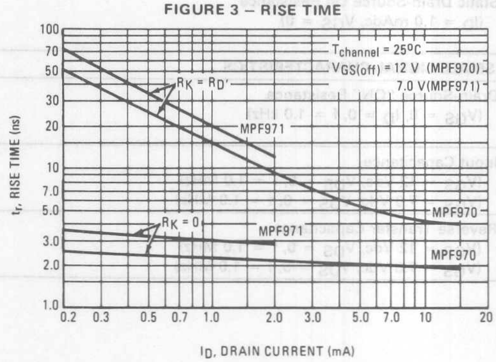


FIGURE 4 — TURN-OFF DELAY TIME

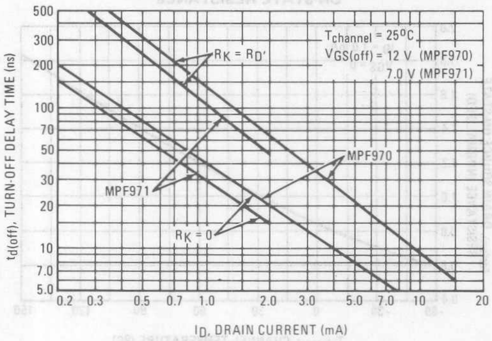


FIGURE 5 FALL TIME

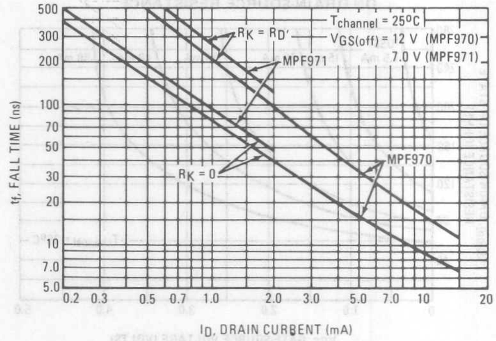
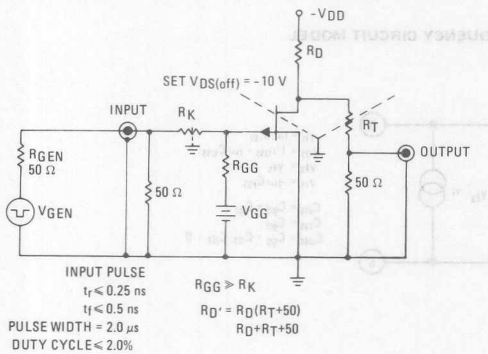


FIGURE 6 — SWITCHING TIME TEST CIRCUIT



NOTE 1

The switching characteristics shown above were measured using a test circuit similar to Figure 6. At the beginning of the switching interval, the gate voltage is at Gate Supply Voltage ($+V_{GG}$). The Drain-Source Voltage (V_{DS}) is slightly lower than Drain Supply Voltage (V_{DD}) due to the voltage divider. Thus Reverse Transfer Capacitance (C_{rss}) or Gate-Drain Capacitance (C_{gd}) is charged to $V_{GG} + V_{DS}$.

During the turn-on interval, Gate-Source Capacitance (C_{gs}) discharges through the series combination of R_{Gen} and R_K. C_{gd} must discharge to $V_{DS(on)}$ through R_G and R_K in series with the parallel combination of effective load impedance (R'_D) and Drain-Source Resistance (r_{ds}). During the turn-off, this charge flow is reversed.

Predicting turn-on time is somewhat difficult as the channel resistance r_{ds} is a function of the gate-source voltage. While C_{gs} discharges, V_{GS} approaches zero and r_{ds} decreases. Since C_{gd} discharges through r_{ds}, turn-on time is non-linear. During turn-off, the situation is reversed with r_{ds} increasing as C_{gd} charges.

The above switching curves show two impedance conditions; 1) R_K is equal to R_D, which simulates the switching behavior of cascaded stages where the driving source impedance is normally the load impedance of the previous stage, and 2) $R_K = 0$ (low impedance) the driving source impedance is that of the generator.

FIGURE 7 — TYPICAL FORWARD TRANSFER ADMITTANCE

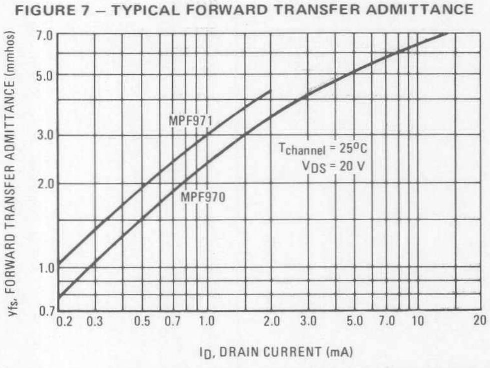
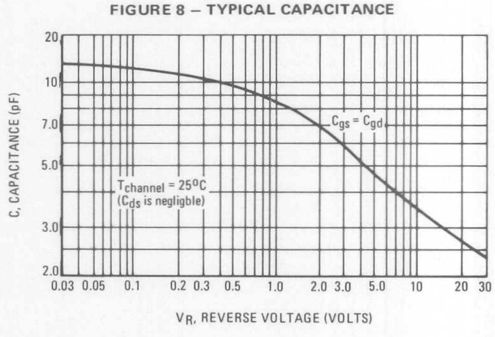


FIGURE 8 — TYPICAL CAPACITANCE



6

FIGURE 9 – EFFECT OF GATE-SOURCE VOLTAGE ON DRAIN-SOURCE RESISTANCE

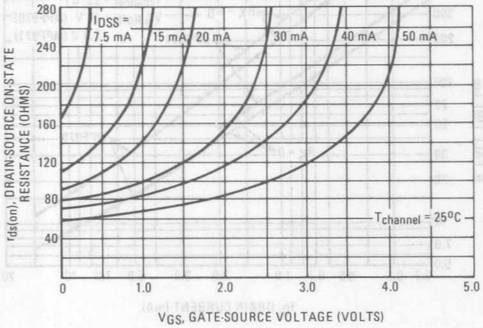


FIGURE 10 – EFFECT OF TEMPERATURE ON DRAIN-SOURCE ON-STATE RESISTANCE

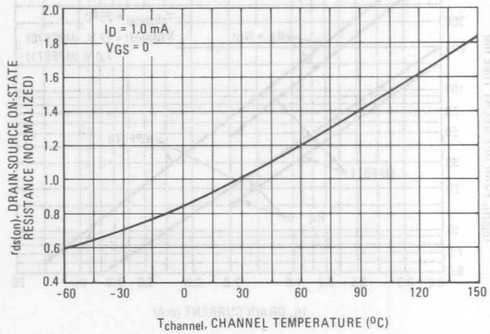
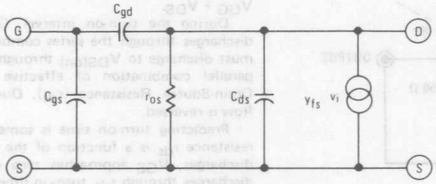


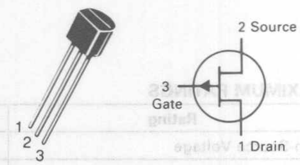
FIGURE 11 – LOW FREQUENCY CIRCUIT MODEL



$y_{is} = j\omega C_{iss}$
$y_{os} = 1/r_{oss} + j\omega C_{oss}$
$y_{fs} = y_{fs}$
$y_{rs} = -j\omega C_{rss}$

$C_{iss} = C_{gd} + C_{gs}$
$C_{rss} = C_{gd}$
$C_{oss} = C_{gd} + C_{ds}, C_{ds} \approx 0$

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
LOW-FREQUENCY, LOW NOISE

P-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V_{DG}	20	Vdc
Gate-Source Voltage	V_{GS}	20	Vdc
Reverse Gate-Source Voltage	V_{GSR}	20	Vdc
Gate Current	I_G	10	mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	310 2.82	mW mW/°C
Storage Temperature Range	T_{stg}	−65 to +150	°C

Refer to 2N5460 for graphs.

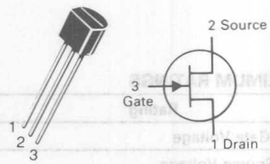
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage ($I_G = 10\ \mu A$)	$V_{(BR)GSS}$	20	—	Vdc
Gate Reverse Current ($V_{GS} = 10$ V)	I_{GSS}	—	10	nA
Gate Source Cutoff Voltage ($V_{DS} = -15$ V, $I_D = 10\ \mu A$)	$V_{GS(off)}$	—	6.0	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current ($V_{DS} = -10$ V)	I_{DSS}*	2.0	6.0	mA
Drain-Source Resistance ($I_D = 100\ \mu A$, $V_{GS} = 0$)	r_{DS}	—	800	Ω
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance ($V_{DS} = -10$ V, $I_D = 2.0$ mA, f = 1.0 kHz)	$\|y_{fs}\|$*	1500	3000	μmhos
Output Admittance ($V_{DS} = -10$ V, $I_D = 2.0$ mA, f = 1.0 kHz)	$\|y_{os}\|$	—	40	μmhos
Input Capacitance ($V_{DS} = -10$ Volts, $V_{GS} = 1.0$ Volt, f = 1.0 MHz)	C_{iss}	—	20	pF
FUNCTIONAL CHARACTERISTICS				
Noise Figure ($V_{DS} = -5.0$ V, $I_D = 1.0$ mA, $R_G = 1.0$ MΩ)	NF	—	3.0	dB

*Pulse Width ≤ 100 ms, Duty Cycle ≤ 10%.

MPF3821
MPF3822

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
GENERAL PURPOSE
N-CHANNEL — DEPLETION

Refer to 2N4220 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	50	Vdc
Drain-Gate Voltage	V_{DG}	50	Vdc
Gate-Source Voltage	V_{GS}	−50	Vdc
Drain Current	I_D	10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	310 2.0	mW mW/°C
Junction Temperature Range	T_J	125	°C
Storage Temperature Range	T_{stg}	−65 to 150	°C

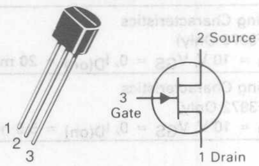
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = −1.0 μAdc, V_{DS} = 0)		$V_{(BR)GSS}$	−50	—	Vdc
Gate Reverse Current (V_{GS} = −30 Vdc, V_{DS} = 0) (V_{GS} = −30 Vdc, V_{DS} = 0, T_A = 150°C)		I_{GSS}	 — —	 −0.1 −100	nAdc
Gate Source Cutoff Voltage (I_D = 0.5 nAdc, V_{DS} = 15 Vdc)	MPF3821 MPF3822	$V_{GS(off)}$	— —	−4.0 −6.0	Vdc
Gate Source Voltage (I_D = 50 μAdc, V_{DS} = 15 Vdc) (I_D = 200 μAdc, V_{DS} = 15 Vdc)	 MPF3821 MPF3822	V_{GS}	 −0.5 −1.0	 −2.0 −4.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current(1) (V_{DS} = 15 Vdc, V_{GS} = 0)	MPF3821 MPF3822	I_{DSS}	0.5 2.0	2.5 10	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)(1)	MPF3821 MPF3822	$\|Y_{fs}\|$	1500 3000	4500 6500	μmhos
(V_{DS} = 15 Vdc, V_{GS} = 0, f = 100 MHz)	MPF3821 MPF3822		1500 3000	— —	
Output Admittance(1) (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 kHz)	MPF3821 MPF3822	$\|Y_{os}\|$	— —	10 20	μmhos
Input Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	6.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	—	3.0	pF
FUNCTIONAL CHARACTERISTICS					
Noise Figure (V_{DS} = 15 Vdc, V_{GS} = 0, R_S = 1.0 megohm, f = 10 Hz, Noise Bandwidth = 5.0 Hz)		NF	—	5.0	dB
Equivalent Input Noise Voltage (V_{DS} = 15 Vdc, V_{GS} = 0, f = 10 Hz, Noise Bandwidth = 5.0 Hz)		e_n	—	200	nv/Hz½

(1) Pulse Test: Pulse Width ≤ 100 ms, Duty Cycle ≤ 10%.

MPF3970
MPF3972

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
SWITCHING

N-CHANNEL — DEPLETION

6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	40	Vdc
Drain-Gate Voltage	V_{DG}	40	Vdc
Reverse Gate-Source Voltage	V_{GSR}	−40	Vdc
Forward Gate Current	I_{GF}	50	mA
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	310 2.82	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = 1.0 μA, V_{GS} = 0)		$V_{(BR)GSS}$	40	—	Vdc
Drain-to-Gate Leakage (V_{DG} = 20 V, I_S = 0)		I_{DGO}	—	250	pA
Gate Reverse Current (V_{GS} = 20 V, V_{DS} = 0)		I_{GSS}	—	250	pA
Gate Source Cutoff Voltage (V_{DS} = −20 V, I_D = 1.0 nA)	 MPF3970 MPF3972	$V_{GS(off)}$	 −4.0 −0.5	 −10 −3.0	Vdc
Drain Source Voltage (V_{GS} = 0) (I_D = 20 mA) (I_D = 5.0 mA)	 MPF3970 MPF3972	V_{GS}	 — —	 1.0 2.0	Vdc
Drain Cutoff Current (V_{DS} = 20 V, V_{GS} = −12 V)		$I_{D(off)}$	—	250	pA
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current (V_{DS} = 20 V, V_{GS} = 0)	 MPF3970 MPF3972	I_{DSS}	 50 5.0	 150 30	mA
Drain-Source "ON" Resistance (I_D = 1.0 mA, V_{GS} = 0)	 MPF3970 MPF3972	$r_{DS(on)}$	 — —	 30 100	Ω
Input Capacitance (V_{DS} = 20 V, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	25	pF
Reverse Transfer Capacitance (V_{DS} = 0, V_{GS} = −12 V, f = 1.0 MHz)		C_{rss}	—	6.0	pF
FUNCTIONAL CHARACTERISTICS					
Drain-Gate Leakage (V_{DG} = 20 V, I_S = 0, T_A = 150°C)		I_{DGO}	—	500	nA
Drain Cutoff Current (V_{DS} = 20 V, V_{GS} = −12 V, T_A = 150°C)		$I_{D(off)}$	—	500	nA

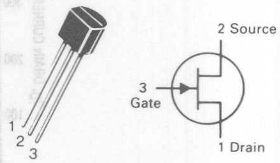
Characteristic		Symbol	Min	Max	Unit
Drain-Source "ON" Resistance (I_D = 0, V_{GS} = 0, f = 1.0 kHz)	MPF3970	$r_{ds(on)}$	—	30	Ω
	MPF3972		—	100	

SWITCHING CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Switching Characteristics (MPF3970 Only) (V_{DD} = 10 V, V_{GS} = 0, $I_{D(on)}$ = 20 mA, $V_{GS(off)}$ = 10 V)	$t_{d(on)}$	—	10	ns
	t_r	—	10	
	t_{off}	—	30	
Switching Characteristics (MPF3972 Only) (V_{DD} = 10 V, V_{GS} = 0, $I_{D(on)}$ = 5.0 mA, $V_{GS(off)}$ = 3.0 V)	$t_{d(on)}$	—	40	ns
	t_r	—	40	
	t_{off}	—	100	

6

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
DC AMPLIFIER TRANSISTOR

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	−40	Vdc
Drain-Gate Voltage	V_{DG}	−40	Vdc
Gate Current	I_G	50	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 2.0	mW mW/°C
Storage Channel Temperature Range	T_{stg}	−65 to +125	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (V_{DS} = 0, I_G = −1.0 μAdc)		$V_{(BR)GSS}$	−40	—	Vdc
Gate Reverse Current (V_{GS} = 20 Vdc, V_{DS} = 0)	MPF4118 MPF4118,A	I_{GSS}	— —	−10 −1.0	pAdc
(V_{GS} = 20 Vdc, V_{DS} = 0, T_A = 125°C)	MPF4118 MPF4118,A		— —	−25 −2.5	nAdc
Gate Source Cutoff Voltage (V_{DS} = 10 Vdc, I_D = 1.0 nAdc)	MPF4118,A	$V_{GS(off)}$	−1.0	−3.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current(1) (V_{DS} = 10 Vdc, V_{GS} = 0)	MPF4118,A	I_{DSS}	0.08	0.24	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Input Capacitance (V_{DS} = 10 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	—	3.0	pF
Reverse Transfer Capacitance (V_{DS} = 10 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	—	1.5	pF
Common-Source Forward Transconductance (V_{DS} = 10 Vdc, V_{GS} = 0, f = 1.0 kHz)	MPF4118,A	g_{fs}	80	250	μmhos
Common-Source Output Conductance (V_{DS} = 10 Vdc, V_{GS} = 0, f = 1.0 kHz)	MPF4118,A	g_{os}	—	5.0	μmhos

(1) I_{DSS} is measured during a 2.0 ms interval 100 ms after power is applied.

6

6

FIGURE 1 — TRANSFER CHARACTERISTICS

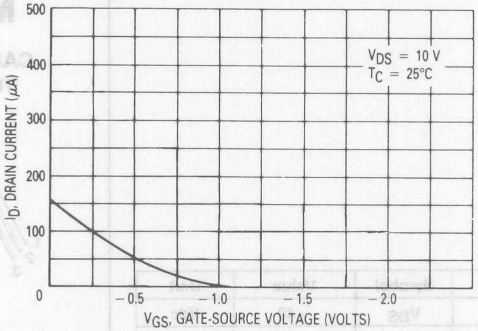


FIGURE 2 — TRANSCONDUCTANCE CHARACTERISTICS

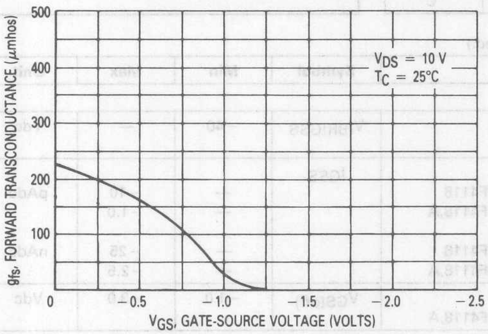
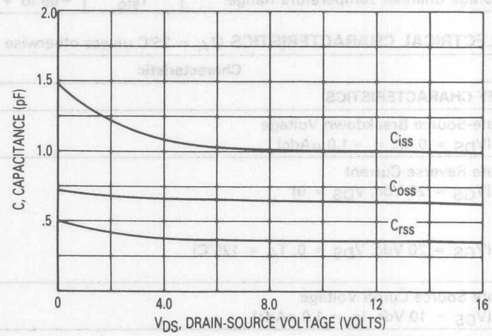
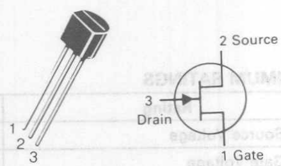


FIGURE 3 — CAPACITANCE versus DRAIN-SOURCE VOLTAGE



MPF4150

CASE 29-04, STYLE 23
TO-92 (TO-226AA)



TMOS FET TRANSISTOR

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	150	Vdc
Drain-Gate Voltage	V_{DG}	150	Vdc
Drain Current — Continuous Pulsed(1)	I_D I_{DM}	250 500	mA
Total Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

(1) The Power Dissipation of the package may result in a lower continuous drain current.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

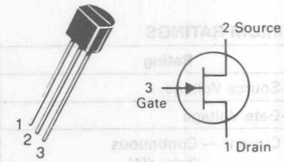
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Breakdown Voltage Drain to Source ($V_{GS} = -10$ V, $I_D = 10\ \mu A$)	$V_{(BR)DSX}$	−150	—	Vdc
Gate-Source Cutoff Voltage ($V_{DS} = 3.5$ V, $I_D = 1.0\ \mu A$)	$V_{GS(off)}$	−1.0	−6.0	Vdc
Gate Reverse Leakage ($V_{GS} = -20$ V, $V_{DS} = 0$)	I_{GSS}	—	1.0	nAdc
ON CHARACTERISTICS				
Zero-Gate Voltage Drain Current(2) ($V_{DS} = 10$ V, $V_{GS} = 0$)	I_{DSS}	−100	−800	mAdc
Static Drain-Source On-Resistance ($V_{GS} = 0$ V, $I_D = 100$ mA)	$r_{DS(on)}$	—	12	Ohms
SMALL-SIGNAL CHARACTERISTICS				
Forward Transadmittance(2) ($V_{DS} = 10$ V, $I_D = 50$ mA, f = 1.0 kHz)	y_{fs}	100	—	mmhos
Input Capacitance ($V_{DS} = 10$ Vdc, $V_{GS} = -10$ V, f = 1.0 MHz)	C_{iss}	—	125	pF
Reverse Transfer Capacitance ($V_{DS} = 10$ V, $V_{GS} = -10$ V, f = 1.0 MHz)	C_{rss}	—	15	pF

(2) Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

6

MPF4221
MPF4222A

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
LOW-FREQUENCY

N-CHANNEL — DEPLETION

Refer to 2N4220 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage	V_{GS}	30	Vdc
Reverse Gate-Source Voltage	V_{GSR}	30	Vdc
Gate Current	I_G	10	mA
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	310 2.82	mW mW/°C
Storage Temperature Range	T_{stg}	−65 to +150	°C

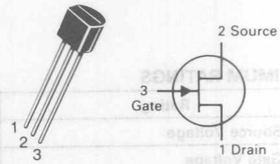
ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = -10\ \mu A$, $V_{DS} = 0$ V)		$V_{(BR)GSS}$	−30	—	Vdc
Gate Reverse Current ($V_{GS} = -15$ V, $V_{DS} = 0$ V)		I_{GSS}	—	−100	pA
Gate Source Cutoff Voltage ($V_{DS} = 15$ V, $I_D = 0.1$ nA)	MPF4221 MPF4222A	$V_{GS(off)}$	— —	−6.0 −8.0	Vdc
Gate Source Voltage ($V_{DS} = 15$ V, $I_D = 200\ \mu A$) ($V_{DS} = 15$ V, $I_D = 500\ \mu A$)	MPF4221 MPF4222A	V_{GS}	−1.0 −2.0	−5.0 −6.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current ($V_{DS} = 15$ Volts, $V_{GS} = 0$ V)	MPF4221 MPF4222A	I_{DSS}*	+2.0 +5.0	+6.0 +15	mA
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance ($V_{DS} = 15$ V, f = 1.0 kHz, $V_{GS} = 0$ V)	MPF4221 MPF4222A	$\|y_{fs}\|$*	2000 2500	5000 6000	µmhos
Output Admittance ($V_{DS} = 15$ V, f = 1.0 kHz, $V_{GS} = 0$ V)	MPF4221 MPF4222A	$\|y_{os}\|$	— —	20 40	µmhos
Input Capacitance ($V_{DS} = 15$ V, f = 1.0 MHz)		C_{iss}	—	6.0	pF
Reverse Transfer Capacitance ($V_{DS} = 15$ V, f = 1.0 MHz)		C_{rss}	—	2.0	pF
FUNCTIONAL CHARACTERISTICS					
Noise Figure ($V_{DS} = 15$ V, f = 100 Hz, $R_G = 1.0$ MΩ)		NF	—	2.5	dB

*Pulse Width ≤ 100 ms, Duty Cycle ≤ 10%.

MPF4223
MPF4224

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
HIGH-FREQUENCY
AMPLIFIER

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Drain Current	I_D	20	mA
Gate Current	I_G	10	mA
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 2.0	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

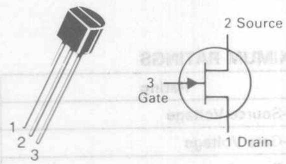
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage (I_G = −10 μA)		$V_{(BR)GSS}$	−30	—	Vdc
Gate 1 Leakage Current (V_{G1S} = −20 V)	MPF4223 MPF4224	I_{G1SS}	— —	0.25 0.50	nA
Gate Source Cutoff Voltage (I_D = 0.25 nA, V_{DS} = 15 V) (I_D = 0.5 nA, V_{DS} = 15 V)	MPF4223 MPF4224	$V_{GS(off)}$	−0.1 −0.1	−8.0 −8.0	Vdc
Gate Source Voltage (I_D = 0.3 mA, V_{DS} = 15 V) (I_D = 0.2 mA, V_{DS} = 15 V)	MPF4223 MPF4224	V_{GS}	−1.0 −1.0	−7.0 −7.5	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current (V_{DS} = 15 V)	MPF4223 MPF4224	I_{DSS}	3.0 2.0	18 20	mA
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance (V_{DS} = 15 V, V_{GS} = 0 V, f = 1.0 kHz)	MPF4223 MPF4224	$\lvert y_{fs} \rvert$	3000 2000	7000 7500	μmhos
Output Conductance (V_{DS} = 15 V, V_{GS} = 0 V, f = 200 MHz)		$Re(y_{os})$	—	200	μmhos
Input Capacitance (V_{DS} = 15 V, V_{GS} = 0 V, f = 1.0 MHz)		C_{iss}	—	6.0	pF
Reverse Transfer Capacitance (V_{DS} = 15 V, V_{GS} = 0 V, f = 1.0 MHz)		C_{rss}	—	2.0	pF
FUNCTIONAL CHARACTERISTICS					
Noise Figure (V_{DS} = 15 V, V_{GS} = 0 V, R_G = 1.0 kΩ, f = 200 MHz)	MPF4223 (Only)	NF	—	5.0	dB
Common Source Power Gain (V_{DS} = 15 V, V_{GS} = 0 V, f = 200 MHz)	MPF4223 (Only)	G_{ps}	10	—	dB

6

6

MPF4391
MPF4392
MPF4393

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET
SWITCHING

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage	V_{GS}	30	Vdc
Forward Gate Current	$I_{G(f)}$	50	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	625 5.0	mW mW/°C
Operating and Storage Channel Temperature Range	$T_{channel}$, T_{stg}	−65 to +150	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Gate-Source Breakdown Voltage ($I_G = 1.0\ \mu Adc$, $V_{DS} = 0$)		$V_{(BR)GSS}$	30		—	Vdc
Gate Reverse Current ($V_{GS} = 15\ Vdc$, $V_{DS} = 0$) ($V_{GS} = 15\ Vdc$, $V_{DS} = 0$, $T_A = 100°C$)		I_{GSS}	 — —	 — —	 1.0 0.2	 nAdc μAdc
Drain-Cutoff Current ($V_{DS} = 15\ Vdc$, $V_{GS} = 12\ Vdc$) ($V_{DS} = 15\ Vdc$, $V_{GS} = 12\ Vdc$, $T_A = 100°C$)		$I_{D(off)}$	 — —		 1.0 0.1	 nAdc μAdc
Gate Source Voltage ($V_{DS} = 15\ Vdc$, $I_D = 10\ nAdc$)	MPF4391 MPF4392 MPF4393	V_{GS}	4.0 2.0 0.5	— — —	10 5.0 3.0	Vdc
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current(1) ($V_{DS} = 15\ Vdc$, $V_{GS} = 0$)	MPF4391 MPF4392 MPF4393	I_{DSS}	60 25 5.0	— — —	130 75 30	mAdc
Drain-Source On-Voltage ($I_D = 12\ mAdc$, $V_{GS} = 0$) ($I_D = 6.0\ mAdc$, $V_{GS} = 0$) ($I_D = 3.0\ mAdc$, $V_{GS} = 0$)	MPF4391 MPF4392 MPF4393	$V_{DS(on)}$	— — —	— — —	0.4 0.4 0.4	Vdc
Static Drain-Source On Resistance ($I_D = 1.0\ mAdc$, $V_{GS} = 0$)	MPF4391 MPF4392 MPF4393	$r_{DS(on)}$	— — —	— — —	30 60 100	Ohms
SMALL-SIGNAL CHARACTERISTICS						
Forward Transfer Admittance ($V_{DS} = 15\ Vdc$, $I_D = 60\ mAdc$, $f = 1.0\ kHz$) ($V_{DS} = 15\ Vdc$, $I_D = 25\ mAdc$, $f = 1.0\ kHz$) ($V_{DS} = 15\ Vdc$, $I_D = 5.0\ mAdc$, $f = 1.0\ kHz$)	MPF4391 MPF4392 MPF4393	$\|y_{fs}\|$	— — —	20 17 12	—	mmhos
Drain-Source "ON" Resistance ($V_{GS} = 0$, $I_D = 0$, $f = 1.0\ kHz$)	MPF4391 MPF4392 MPF4393	$r_{ds(on)}$	— — —	— — —	30 60 100	Ohms
Input Capacitance ($V_{GS} = 15\ Vdc$, $V_{DS} = 0$, $f = 1.0\ MHz$)		C_{iss}	—	6.0	10	pF

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
Reverse Transfer Capacitance		C_{rss}				pF
(V_{GS} = 12 Vdc, V_{DS} = 0, f = 1.0 MHz)			—	2.5	3.5	
(V_{DS} = 15 Vdc, I_D = 10 mAdc, f = 1.0 MHz)			—	3.2	—	
SWITCHING CHARACTERISTICS						
Rise Time (See Figure 2)		t_r				ns
($I_{D(on)}$ = 12 mAdc)	MPF4391		—	1.2	5.0	
($I_{D(on)}$ = 6.0 mAdc)	MPF4392		—	2.0	5.0	
($I_{D(on)}$ = 3.0 mAdc)	MPF4393		—	2.5	5.0	
Fall Time (See Figure 4)		t_f				ns
($V_{GS(off)}$ = 12 Vdc)	MPF4391		—	7.0	15	
($V_{GS(off)}$ = 7.0 Vdc)	MPF4392		—	15	20	
($V_{GS(off)}$ = 5.0 Vdc)	MPF4393		—	29	35	
Turn-On Time (See Figures 1 and 2)		t_{on}				ns
($I_{D(on)}$ = 12 mAdc)	MPF4391		—	3.0	15	
($I_{D(on)}$ = 6.0 mAdc)	MPF4392		—	4.0	15	
($I_{D(on)}$ = 3.0 mAdc)	MPF4393		—	6.5	15	
Turn-Off Time (See Figures 3 and 4)		t_{off}				ns
($V_{GS(off)}$ = 12 Vdc)	MPF4391		—	10	20	
($V_{GS(off)}$ = 7.0 Vdc)	MPF4392		—	20	35	
($V_{GS(off)}$ = 5.0 Vdc)	MPF4393		—	37	55	

(1) Pulse Test: Pulse Width ≤ 100 μs, Duty Cycle ≤ 1.0%.

6

TYPICAL SWITCHING CHARACTERISTICS

FIGURE 1 – TURN-ON DELAY TIME

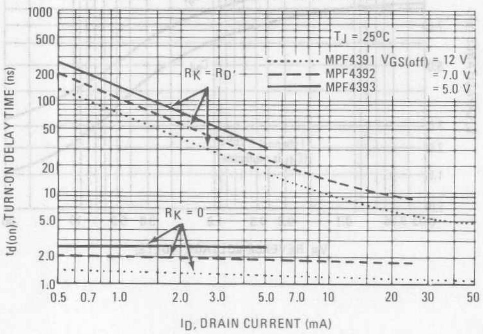


FIGURE 2 – RISE TIME

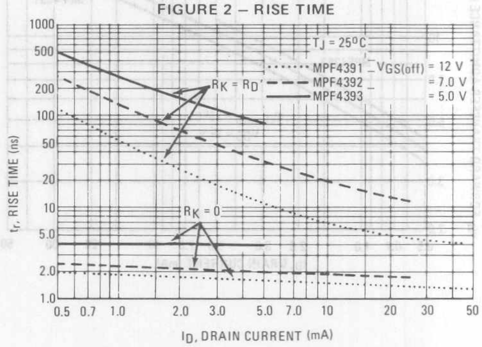


FIGURE 3 – TURN-OFF DELAY TIME

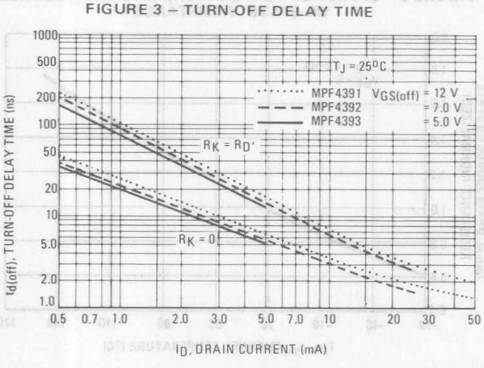
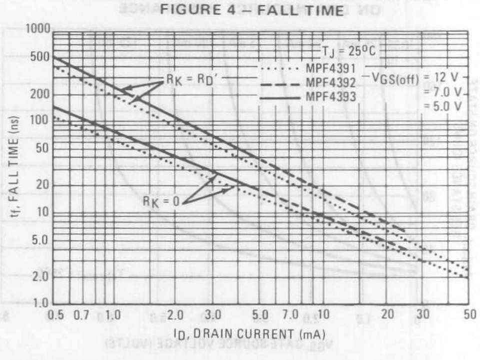
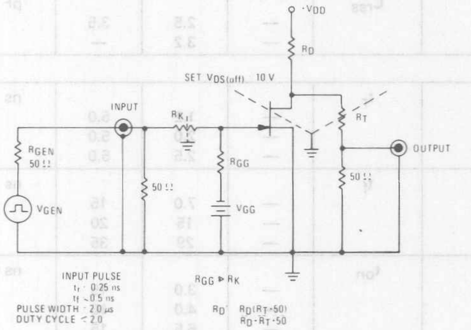


FIGURE 4 – FALL TIME





test circuit similar to Figure 5. At the beginning of the switching interval, the gate voltage is at Gate Supply Voltage ($-V_{GG}$). The Drain-Source Voltage (V_{DS}) is slightly lower than Drain Supply Voltage (V_{DD}) due to the voltage divider. Thus Reverse Transfer Capacitance (C_{rss}) or Gate-Drain Capacitance (C_{gd}) is charged to $V_{GG} + V_{DS}$.

During the turn-on interval, Gate-Source Capacitance (C_{gs}) discharges through the series combination of R_{Gen} and R_K. C_{gd} must discharge to $V_{DS(on)}$ through R_G and R_K in series with the parallel combination of effective load impedance (R'_D) and Drain-Source Resistance (r_{ds}). During the turn-off, this charge flow is reversed.

Predicting turn-on time is somewhat difficult as the channel resistance r_{ds} is a function of the gate-source voltage. While C_{gs} discharges, V_{GS} approaches zero and r_{ds} decreases. Since C_{gd} discharges through r_{ds}, turn-on time is non-linear. During turn-off, the situation is reversed with r_{ds} increasing as C_{gd} charges.

The above switching curves show two impedance conditions; 1) R_K is equal to $R_{D'}$, which simulates the switching behavior of cascaded stages where the driving source impedance is normally the load impedance of the previous stage, and 2) $R_K = 0$ (low impedance) the driving source impedance is that of the generator.

FIGURE 6 – TYPICAL FORWARD TRANSFER ADMITTANCE

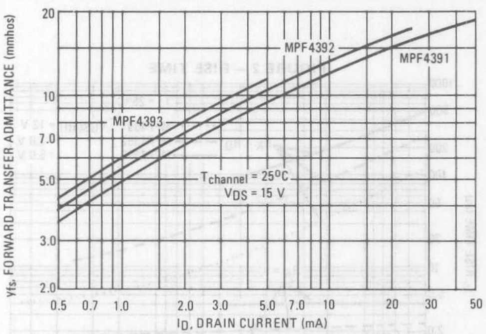


FIGURE 7 – TYPICAL CAPACITANCE

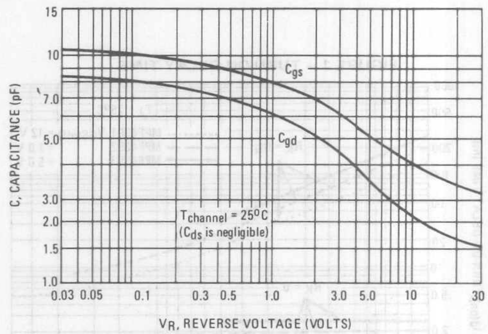


FIGURE 8 – EFFECT OF GATE-SOURCE VOLTAGE ON DRAIN-SOURCE RESISTANCE

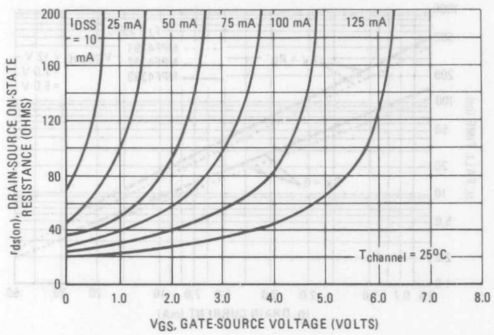


FIGURE 9 – EFFECT OF TEMPERATURE ON DRAIN–SOURCE ON-STATE RESISTANCE

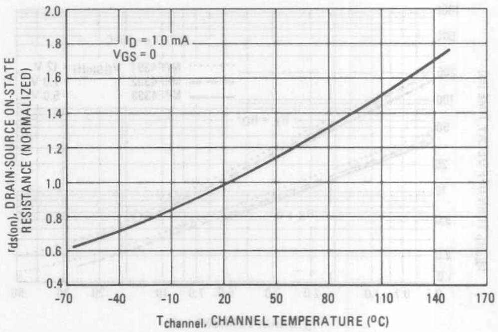
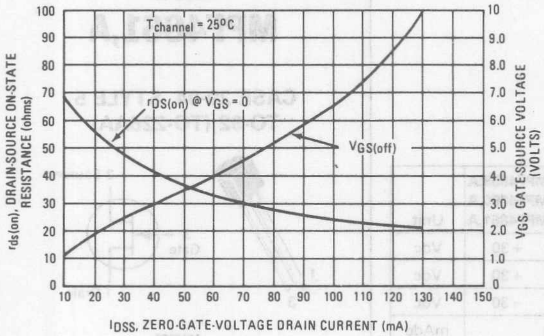


FIGURE 10 — EFFECT OF IDSS ON DRAIN-SOURCE RESISTANCE AND GATE-SOURCE VOLTAGE



NOTE 2

The Zero-Gate-Voltage Drain Current (I_{DSS}), is the principle determinant of other J-FET characteristics. Figure 10 shows the relationship of Gate-Source Off Voltage ($V_{GS(off)}$) and Drain-Source On Resistance ($r_{ds(on)}$) to I_{DSS}. Most of the devices will be within ±10% of the values shown in Figure 10. This data will be useful in predicting the characteristic variations for a given part number.

For example:

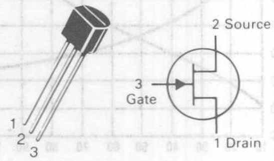
Unknown

$r_{ds(on)}$ and V_{GS} range for an MPF4392

The electrical characteristics table indicates that an MPF4392 has an I_{DSS} range of 25 to 75 mA. Figure 10, shows $r_{ds(on)}$ = 52 Ohms for I_{DSS} = 25 mA and 30 Ohms for I_{DSS} = 75 mA. The corresponding V_{GS} values are 2.2 volts and 4.8 volts.

MPF4856,A thru MPF4861,A

CASE 29-04, STYLE 5
TO-92 (TO-226AA)



JFET SWITCHING

N-CHANNEL — DEPLETION

Refer to 2N4856 for graphs.

MAXIMUM RATINGS

Rating	Symbol	MPF4856,A MPF4857,A MPF4858,A	MPF4859,A MPF4860,A MPF4861,A	Unit
Drain-Source Voltage	V_{DS}	+40	+30	Vdc
Drain-Gate Voltage	V_{DG}	+40	+30	Vdc
Reverse Gate-Source Voltage	V_{GSR}	−40	−30	Vdc
Forward Gate Current	I_{GF}	50		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	360 2.4		mW mW/°C
Storage Temperature Range	T_{stg}	−65 to +150		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage		$V_{(BR)GSS}$			Vdc
(I_G = 1.0 μAdc, V_{DS} = 0)	MPF4856,A, MPF4857,A, MPF4858,A		−40	—	
	MPF4859,A, MPF4860,A, MPF4861,A		−30	—	
Gate Reverse Current		I_{GSS}			
(V_{GS} = −20 Vdc, V_{DS} = 0)	MPF4856,A, MPF4857,A, MPF4858,A		—	0.25	nAdc
(V_{GS} = −15 Vdc, V_{DS} = 0)	MPF4859,A, MPF4860,A, MPF4861,A		—	0.25	
(V_{GS} = −20 Vdc, V_{DS} = 0, T_A = 150°C)	MPF4856,A, MPF4857,A, MPF4858,A		—	0.5	μAdc
(V_{GS} = −15 Vdc, V_{DS} = 0, T_A = 150°C)	MPF4859,A, MPF4860,A, MPF4861,A		—	0.5	
Gate Source Cutoff Voltage		$V_{GS(off)}$			Vdc
(V_{DS} = 15 Vdc, I_D = 0.5 nAdc)	MPF4856,A, MPF4859,A		−4.0	−10	
	MPF4857,A, MPF4860,A		−2.0	−6.0	
	MPF4858,A, MPF4861,A		−0.8	−4.0	
Drain Cutoff Current		$I_{D(off)}$			
(V_{DS} = 15 Vdc, V_{GS} = −10 Vdc)			—	0.25	nAdc
(V_{DS} = 15 Vdc, V_{GS} = −10 Vdc, T_A = 150°C)			—	0.5	μAdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current(1)		I_{DSS}			mAdc
(V_{DS} = 15 Vdc, V_{GS} = 0)	MPF4856,A, MPF4859,A		50	—	
	MPF4857,A, MPF4860,A		20	100	
	MPF4858,A, MPF4861,A		8.0	80	
Drain-Source On-Voltage		$V_{DS(on)}$			Vdc
(I_D = 20 mAdc, V_{GS} = 0)	MPF4856,A, MPF4859,A		—	0.75	
(I_D = 10 mAdc, V_{GS} = 0)	MPF4857,A, MPF4860,A		—	0.5	
(I_D = 5.0 mAdc, V_{GS} = 0)	MPF4858,A, MPF4861,A		—	0.5	
SMALL-SIGNAL CHARACTERISTICS					
Drain-Source "ON" Resistance		$r_{ds(on)}$			Ohms
(V_{GS} = 0, I_D = 0, f = 1.0 kHz)	MPF4856,A, MPF4859,A		—	25	
	MPF4857,A, MPF4860,A		—	40	
	MPF4858,A, MPF4861,A		—	60	
Input Capacitance		C_{iss}			pF
(V_{DS} = 0, V_{GS} = −10 Vdc, f = 1.0 MHz)	MPF4856 thru MPF4861		—	18	
	MPF4856A thru MPF4861A		—	10	
Reverse Transfer Capacitance		C_{rss}			pF
(V_{DS} = 0, V_{GS} = −10 Vdc, f = 1.0 MHz)	MPF4856 thru MPF4861		—	8.0	
	MPF4856A, MPF4859A		—	4.0	
	MPF4857A, MPF4858A, MPF4860A, MPF4861A		—	3.5	

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Characteristic			Symbol	Min	Max	Unit
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	Conditions for MPF4856,A, MPF4859,A:	MPF4856, MPF4859	$t_{d(on)}$	—	6.0	ns
		MPF4856A, MPF4859A		—	5.0	
	(V_{DD} = 10 Vdc, $I_{D(on)}$ = 20 mAdc,	MPF4857, MPF4860		—	6.0	
	$V_{GS(on)}$ = 0, $V_{GS(off)}$ = −10 Vdc)	MPF4857A, MPF4860A		—	6.0	
		MPF4858, MPF4861		—	10	
		MPF4858A, MPF4861A		—	8.0	
Rise Time	Conditions for MPF4857,A, MPF4860,A:	MPF4856,A, MPF4859,A	t_r	—	3.0	ns
		MPF4857,A, MPF4860,A		—	4.0	
	(V_{DD} = 10 Vdc, $I_{D(on)}$ = 10 mAdc,	MPF4858, MPF4861		—	10	
	$V_{GS(on)}$ = 0, $V_{GS(off)}$ = −6.0 Vdc)	MPF4858A, MPF4861A		—	8.0	
Turn-Off Time		MPF4856, MPF4859	t_{off}	—	25	
	Conditions for MPF4858,A, MPF4861,A:	MPF4856A, MPF4859A		—	20	ns
		MPF4857, MPF4860		—	50	
	(V_{DD} = 10 Vdc, $I_{D(on)}$ = 5.0 mAdc,	MPF4857A, MPF4860A		—	40	
	$V_{GS(on)}$ = 0, $V_{GS(off)}$ = −4.0 Vdc)	MPF4858, MPF4861		—	100	
		MPF4858A; MPF4861A		—	80	

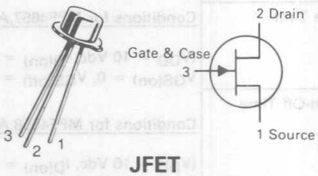
(1) Pulse Test: Pulse Width = 100 ms, Duty Cycle ≤ 10%.
(2) The $I_{D(on)}$ values are nominal; exact values vary slightly with transistor parameters.

6

MPF6659 thru 6661 For Specifications, See 2N6659 Data.

U308
U309
U310

CASE 27-02, STYLE 4
TO-52 (TO-206AC)



JFET
VHF/UHF AMPLIFIER

N-CHANNEL — DEPLETION

MAXIMUM RATINGS

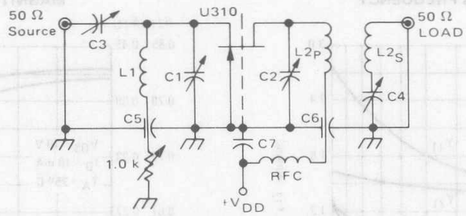
Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Gate-Source Voltage	V_{GS}	25	Vdc
Gate Current	I_G	20	mAdc
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	500 4.0	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Gate-Source Breakdown Voltage ($I_G = 1.0\ \mu A$, $V_{DS} = 0$)		$V_{(BR)GSS}$	−25	—	—	V
Gate Reverse Current ($V_{GS} = -15$ V)		I_{GSS}	—	—	−150	pA
($V_{GS} = 0$, $T_A = 125°C$)			—	—	−150	nA
Gate Source Cutoff Voltage ($V_{DS} = 10$ V, $I_D = 1.0$ nA)	U308	$V_{GS(off)}$	−1.0	—	−6.0	V
	U309		−1.0	—	−4.0	
	U310		−2.5	—	−6.0	
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current(1) ($V_{DS} = 10$ V, $V_{GS} = 0$)	U308	I_{DSS}	12	—	60	mA
	U309		12	—	30	
	U310		24	—	60	
Gate-Source Forward Voltage ($I_G = 10$ mA, $V_{DS} = 0$)		$V_{GS(f)}$	—	—	1.0	V
SWITCHING CHARACTERISTICS						
Common-Gate Forward Transconductance(1) ($V_{DS} = 10$ V, $I_D = 10$ mA, f = 1.0 kHz)	U308	g_{fg}	10	—	20	mmhos
	U309		10	—	20	
	U310		10	—	18	
Common-Gate Output Conductance ($V_{DS} = 10$ V, $I_D = 10$ mA, f = 1.0 kHz)		g_{og}	—	150	—	µmhos
Drain-Gate Capacitance ($V_{GS} = -10$ V, $V_{DS} = 10$ V, f = 1.0 MHz)		C_{gd}	—	—	2.5	pF
Gate-Source Capacitance ($V_{GS} = -10$ V, $V_{DS} = 10$ V, f = 1.0 MHz)		C_{gs}	—	—	5.0	pF
Equivalent Short-Circuit Input Noise Voltage ($V_{DS} = 10$ V, $I_D = 10$ mA, f = 100 Hz)		$\bar{e}_n$	—	10	—	$nV\sqrt{Hz}$

(1) Pulse test duration = 2.0 ms.
(2) See Figures 10 and 11 for Noise Figure and Power Gain information.

FIGURE 1 – 450 MHz COMMON-GATE AMPLIFIER TEST CIRCUIT



C1 = C2 = 0.8 – 10 pF, JFD #MVM010W.
C3 = C4 = 8-35 pF Erie #539-002D.
C5 = C6 = 5000 pF Erie (2443-000).
C7 = 1000 pF, Allen Bradley #FA5C.
RFC = 0.33 μH Miller #9230-30.
L1 = One Turn #16 Cu, 1/4" I.D. (Air Core).
L2p = One Turn #16 Cu, 1/4" I.D. (Air Core).
L2s = One Turn #16 Cu, 1/4" I.D. (Air Core).

FIGURE 2 – DRAIN CURRENT and TRANSFER CHARACTERISTICS versus GATE-SOURCE VOLTAGE

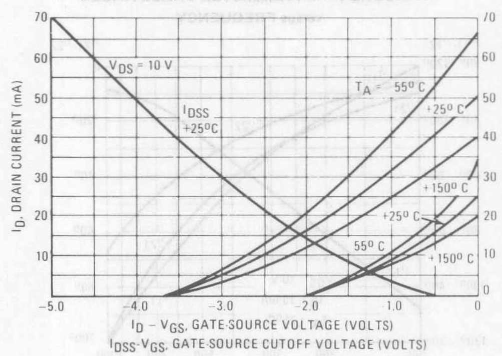


FIGURE 3 – FORWARD TRANSCONDUCTANCE versus GATE-SOURCE VOLTAGE

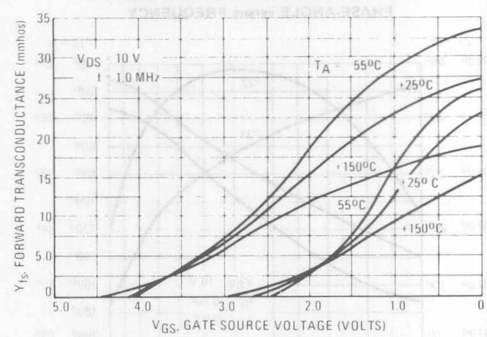


FIGURE 4 – COMMON-SOURCE OUTPUT ADMITTANCE and FORWARD TRANSCONDUCTANCE versus DRAIN CURRENT

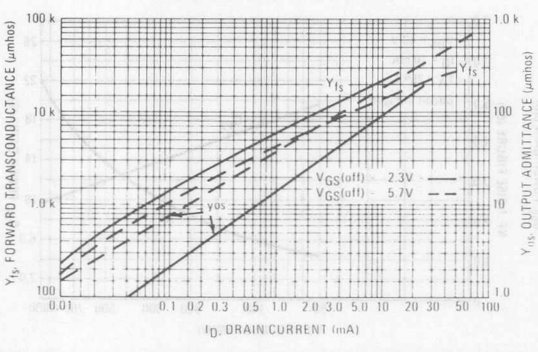


FIGURE 5 – ON RESISTANCE and JUNCTION CAPACITANCE versus GATE-SOURCE VOLTAGE

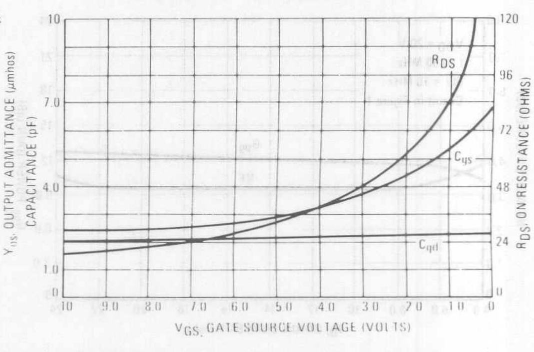


FIGURE 6 – COMMON-GATE Y PARAMETER MAGNITUDE versus FREQUENCY

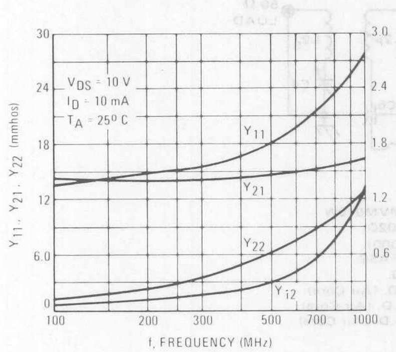


FIGURE 7 – COMMON-GATE S PARAMETER MAGNITUDE versus FREQUENCY

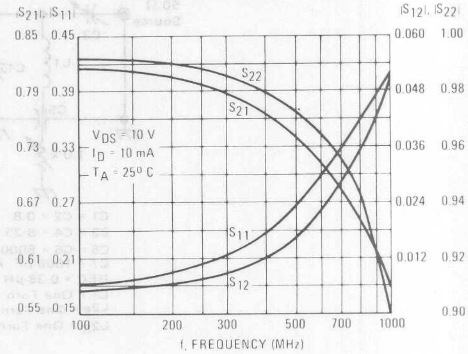


FIGURE 8 – COMMON-GATE Y PARAMETER PHASE-ANGLE versus FREQUENCY

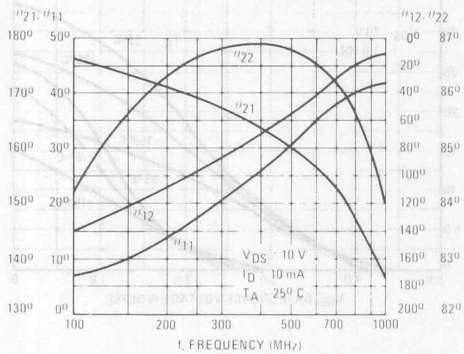


FIGURE 9 – S PARAMETER PHASE-ANGLE versus FREQUENCY

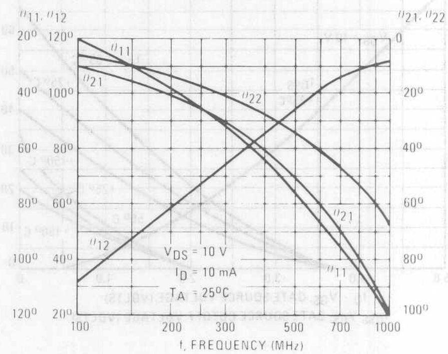


FIGURE 10 – NOISE FIGURE and POWER GAIN versus DRAIN CURRENT

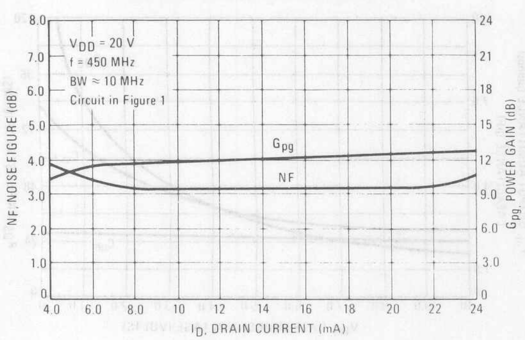


FIGURE 11 – NOISE FIGURE and POWER GAIN versus FREQUENCY

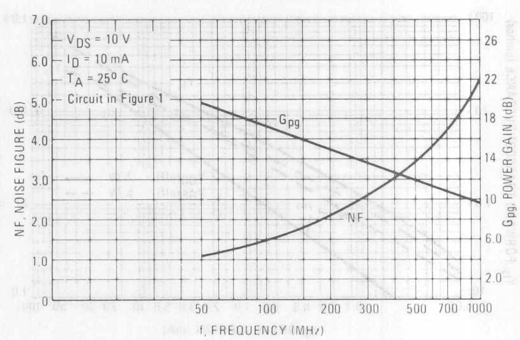
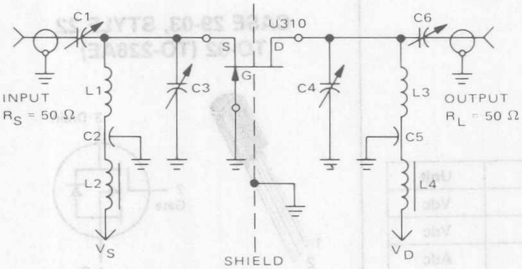


FIGURE 12 – 450 MHz IMD EVALUATION AMPLIFIER

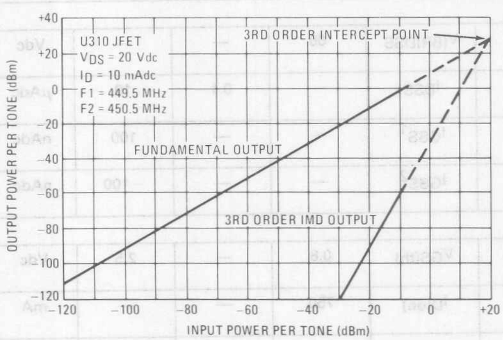


B_W (3dB) = 36.5 MHz
I_D = 10 mAdc
V_{DS} = 20 Vdc
Device case grounded
IM test tones – f1 = 449.5 MHz, f2 = 450.5 MHz

C1 = 1-10 pf Johanson Air variable trimmer.
C2, C5 = 100 pf feed thru button capacitor.
C3, C4, C6 = 0.5-6 pf Johanson Air variable trimmer.
L1 = 1/8" x 1/32" x 1-5/8" copper bar.
L2, L4 = Ferroxcube Vk200 choke.
L3 = 1/8" x 1/32" x 1-7/8" copper bar.

Amplifier power gain and IMD products are a function of the load impedance. For the amplifier design shown above with C4 and C6 adjusted to reflect a load to the drain resulting in a nominal power gain of 9 dB, the 3rd order intercept point (IP) value is 29 dBm. Adjusting C4, C6 to provide larger load values will result in higher gain, smaller bandwidth and lower IP values. For example, a nominal gain of 13 dB can be achieved with an intercept point of 19 dBm.

FIGURE 13 – TWO TONE 3RD ORDER INTERCEPT POINT

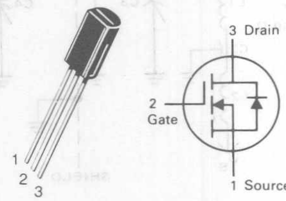


Example of intercept point plot use:
Assume two in-band signals of –20 dBm at the amplifier input. They will result in a 3rd order IMD signal at the output of –90 dBm. Also, each signal level at the output will be –11 dBm, showing an amplifier gain of 9.0 dB and an intermodulation ratio (IMR) capability of 79 dB. The gain and IMR values apply only for signal levels below compression.

6

VN10LM

CASE 29-03, STYLE 22
TO-92 (TO-226AE)



TMOS FET TRANSISTOR

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	Vdc
Gate-Source Voltage	V_{GS}	±30	Vdc
Drain Current — Continuous(1) Pulsed(2)	I_D I_{DM}	0.3 1.0	Adc
Total Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	1.0 8.0	Watts mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−40 to +150	°C

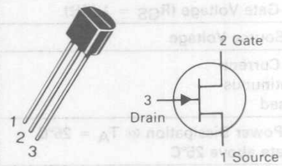
(1) The Power Dissipation of the package may result in a lower continuous drain current.
(2) Pulse Width ≤ 300 μs, Duty Cycle.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage ($V_{GS} = 0$, $I_D = 100\ \mu A$)	$V_{(BR)DSS}$	60	—	—	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = 45$ V, $V_{GS} = 0$)	I_{DSS}	—	0.1	10	μAdc
Gate-Body Leakage Current ($V_{GS} = -15$ V, $V_{DS} = 0$)	I_{GSS}^{1}	—	—	100	nAdc
Gate-Body Leakage Current ($V_{GS} = 15$ V, $V_{DS} = 0$)	I_{GSS}^{2}	—	—	−100	nAdc
ON CHARACTERISTICS					
Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = 1.0$ mA)	$V_{GS(th)}$	0.8	—	2.5	Vdc
On-State Drain Current ($V_{DS} = 15$ V, $V_{GS} = 10$ V)	$I_{D(on)}$	750	—	—	mA
Forward Transconductance ($V_{DS} = 15$ V, $I_D = 500$ mA)	g_{fs}	200	—	—	mmhos
Drain-Source On-Voltage ($V_{GS} = 5.0$ V, $I_D = 200$ mA)	$V_{DS(on)}^{1}$	—	—	1.5	Vdc
Drain-Source On-Voltage ($V_{GS} = 10$ V, $I_D = 500$ mA)	$V_{DS(on)}^{2}$	—	—	2.5	Vdc
Drain-Source On-Resistance ($V_{GS} = 5.0$ V, $I_D = 200$ mA)	$r_{DS(on)}^{1}$	—	—	7.5	Ω
Drain-Source On-Resistance ($V_{GS} = 10$ V, $I_D = 500$ mA)	$r_{DS(on)}^{2}$	—	—	5.0	Ω
Input Capacitance ($V_{DS} = 25$ V, $V_{GS} = 0$, f = 1.0 MHz)	C_{iss}	—	—	60	pF
Output Capacitance ($V_{DS} = 25$ V, $V_{GS} = 0$, f = 1.0 MHz)	C_{oss}	—	—	25	pF
Reverse Transfer Capacitance ($V_{DS} = 25$ V, $V_{GS} = 0$ V, f = 1.0 MHz)	C_{rss}	—	—	5.0	pF
Turn-On Time ($V_{DS} = 15$ V, $R_L = 23\ \Omega$, $R_G = 50\ \Omega$, $V_{in} = 20$ V)	t_{on}	—	—	10	ns
Turn-Off Time ($V_{DS} = 15$ V, $R_L = 23\ \Omega$, $R_G = 50\ \Omega$, $V_{in} = 20$ V)	t_{off}	—	—	10	ns

VN0610LL

CASE 29-04, STYLE 22
TO-92 (TO-226AA)



TMOS FET
TRANSISTOR

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	Vdc
Drain-Gate Voltage (R_{GS} = 1 MΩ)	V_{DGR}	60	Vdc
Gate-Source Voltage	V_{GS}	±40	Vdc
Drain Current Continuous Pulsed	 I_D I_{DM}	 190 1000	mAdc
Total Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	400 3.2	mW mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Thermal Resistance Junction to Ambient	$R_{\theta JA}$	312.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/16″ from case for 10 seconds	T_L	300	°C

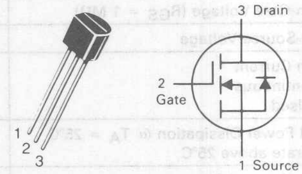
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 100 μA)		$V_{(BR)DSS}$	60	—	Vdc
Zero Gate Voltage Drain Current (V_{DS} = 48 V, V_{GS} = 0) (V_{DS} = 48 V, V_{GS} = 0, T_J = 125°C)		I_{DSS}	 — —	 10 500	μAdc
Gate-Body Leakage Current, Forward (V_{GSF} = 30 Vdc, V_{DS} = 0)		I_{GSSF}	—	100	nAdc
ON CHARACTERISTICS*					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.0 mA)		$V_{GS(th)}$	0.8	2.5	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 500 mA) (V_{GS} = 10 Vdc, I_D = 500 mA, T_C = 125°C)		$r_{DS(on)}$	 — —	 5.0 9.0	Ohm
Drain-Source On-Voltage (V_{GS} = 5.0 V, I_D = 200 mA) (V_{GS} = 10 V, I_D = 500 mA)		$V_{DS(on)}$	 — —	 1.5 2.5	Vdc
On-State Drain Current (V_{GS} = 10 V, V_{DS} ≥ 2.0 $V_{DS(on)}$)		$I_{D(on)}$	750	—	mA
Forward Transconductance (V_{DS} ≥ 2.0 $V_{DS(on)}$, I_D = 500 mA)		g_{fs}	100	—	μmhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0 f = 1.0 MHz)	C_{iss}	—	60	pF
Output Capacitance		C_{oss}	—	25	
Reverse Transfer Capacitance		C_{rss}	—	5.0	
SWITCHING CHARACTERISTICS*					
Turn-On Delay Time	(V_{DD} = 15 V, I_D = 600 mA R_{gen} = 25 ohms, R_L = 23 ohms)	t_{on}	—	10	ns
Turn-Off Delay Time		t_{off}	—	10	

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

VN2222LL

CASE 29-04, STYLE 22
TO-92 (TO-226AA)



TMOS FET
TRANSISTOR

N-CHANNEL — ENHANCEMENT

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	Vdc
Drain-Gate Voltage (R_{GS} = 1 MΩ)	V_{DGR}	60	Vdc
Gate-Source Voltage	V_{GS}	±40	Vdc
Drain Current Continuous Pulsed	 I_D I_{DM}	 150 1000	mAdc
Total Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	400 3.2	mW mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	312.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/16″ from case for 10 seconds	T_L	300	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V_{GS} = 0, I_D = 100 μA)		$V_{(BR)DSS}$	60	—	Vdc
Zero Gate Voltage Drain Current (V_{DS} = 48 V, V_{GS} = 0) (V_{DS} = 48 V, V_{GS} = 0, T_J = 125°C)		I_{DSS}	 — —	 10 500	μAdc
Gate-Body Leakage Current, Forward (V_{GSF} = 30 Vdc, V_{DS} = 0)		I_{GSSF}	—	100	nAdc
ON CHARACTERISTICS*					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.0 mA)		$V_{GS(th)}$	0.6	2.5	Vdc
Static Drain-Source On-Resistance (V_{GS} = 10 Vdc, I_D = 0.5 Adc) (V_{GS} = 10 Vdc, I_D = 0.5 V, T_C = 125°C)		$r_{DS(on)}$		 7.5 13.5	Ohm
Drain-Source On-Voltage (V_{GS} = 5.0 V, I_D = 200 mA) (V_{GS} = 10 V, I_D = 500 mA)		$V_{DS(on)}$	 — —	 1.5 3.75	Vdc
On-State Drain Current (V_{GS} = 10 Vdc, V_{DS} ≥ 2.0 $V_{DS(on)}$)		$I_{D(on)}$	750		mA
Forward Transconductance (V_{DS} = 10 V, I_D = 500 mA)		g_{fs}	100	—	μmhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	(V_{DS} = 25 V, V_{GS} = 0 f = 1.0 MHz)	C_{iss}	—	60	pF
Output Capacitance		C_{oss}	—	25	
Reverse Transfer Capacitance		C_{rss}	—	5.0	
SWITCHING CHARACTERISTICS*					
Turn-On Delay Time	(V_{DD} = 15 V, I_D = 600 mA R_{gen} = 25 ohms, R_L = 23 ohms)	t_{on}	—	10	ns
Turn-Off Delay Time		t_{off}	—	10	

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

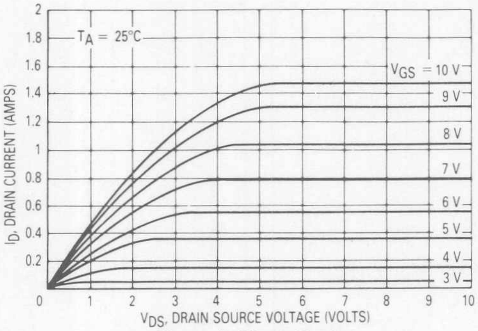


Figure 1. Ohmic Region

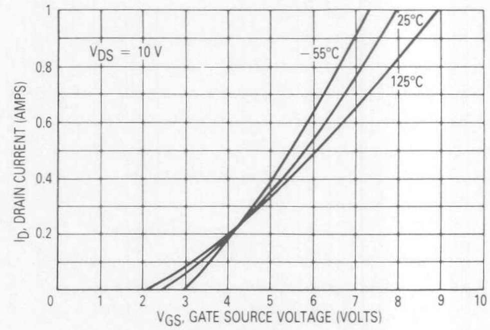


Figure 2. Transfer Characteristics

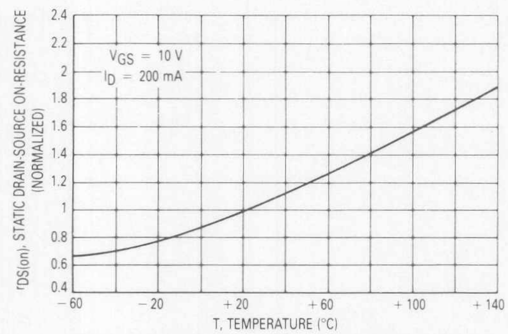


Figure 3. Temperature versus Static Drain-Source On-Resistance

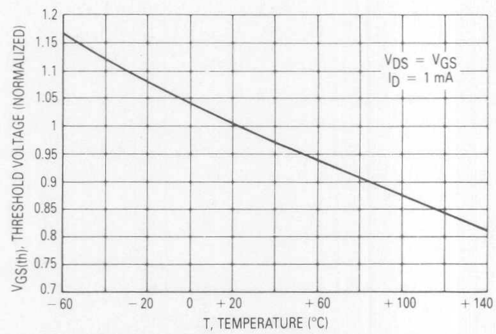


Figure 4. Temperature versus Gate Threshold Voltage

6

Tape and Reel Specifications

7

Embossed Tape and Reel

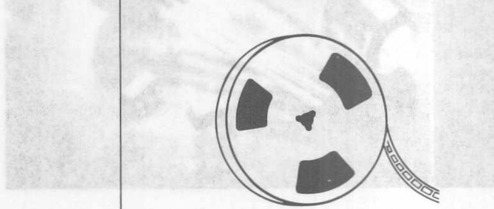
Embossed Tape and Reel is used to facilitate automatic pick and place equipment feed requirements. The tape is used as the shipping container for various products and requires a minimum of handling. The antistatic/conductive tape provides a secure cavity for the product when sealed with the "peel-back" cover tape.

- Two Reel Sizes Available (7" and 13")
- Used For Automatic Pick and Place Feed Systems
- Minimizes Product Handling
- EIA 481
- MLL-34, SOT-23, SOT-143 in 8 mm Tape
- MLL-41, SO-8 in 12 mm Tape
- DPAK, SO-14, SO-16 in 16 mm Tape

Ordering Information

Use the standard device title and add the required suffix as listed in the option table below. Note that the individual reels have a finite number of devices depending on the type of product contained in the tape. Also note the minimum lot size is one full reel for each line item, and orders are required to be in increments of the single reel quantity. Minimum order $200.00/line-line.

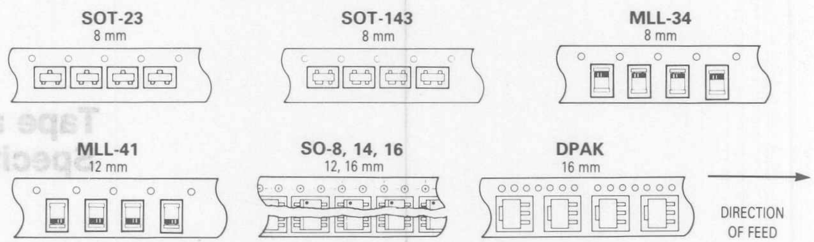
Tape and Reel Data for Discrete Surface Mount Devices



PACKAGES

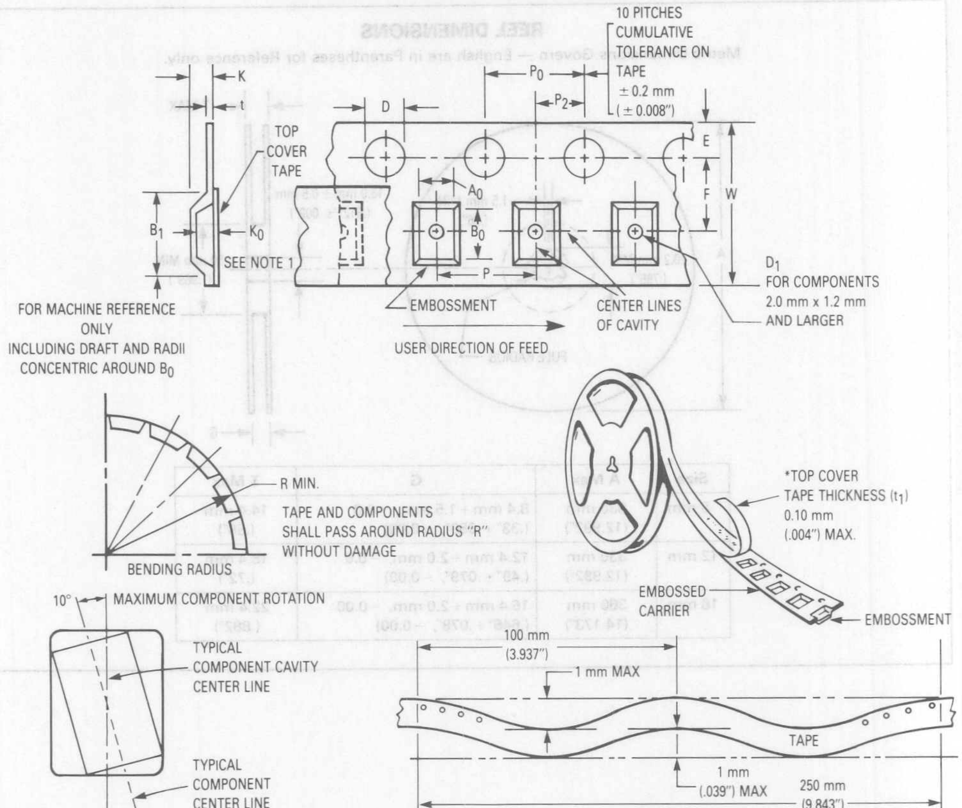
MLL-34	SO-8
MLL-41	SO-14
SOT-23	SO-16
SOT-143	DPAK

7



Package	Tape Width (mm)	Device per Reel	Reel Size (inch)	Tape & Reel Lot Size (Min)	Device Suffix
SOT-23	8 8	3,000 10,000	7 13	3,000 10,000	T1 T3
SOT-143	8 8	3,000 10,000	7 13	3,000 10,000	T1 T3
MLL-34	8 8	2,000 5,000	7 13	2,000 5,000	T1 T3
MLL-41	12 12	1,000 5,000	7 13	1,000 5,000	T1 T3
SO-8	12 12	500 2,500	7 13	500 2,500	R1 R2
SO-14	16 16	500 2,500	7 13	500 2,500	R1 R2
SO-16	16 16	500 2,500	7 13	500 2,500	R1 R2
DPAK	16	1,800	13	1,800	RL

CARRIER TAPE SPECIFICATIONS



CAMBER (TOP VIEW)

ALLOWABLE CAMBER TO BE 1 mm/100 mm NONACCUMULATIVE OVER 250 mm

DIMENSIONS

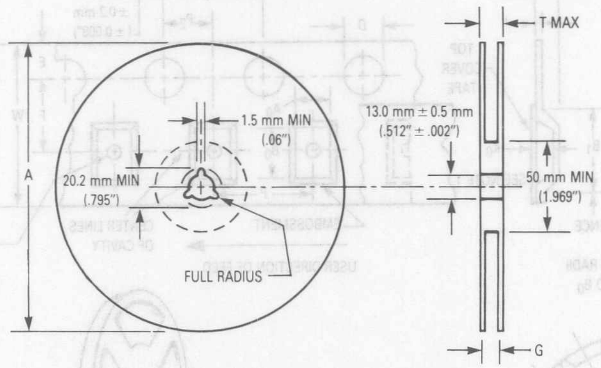
Tape Size	B_1 Max	D	D_1	E	F	K	P	P_0	P_2	R Min	T Max	W
8 mm	4.2 mm (.165")	1.5 + 0.1 mm − 0.0 (.059 + .004" − 0.0)	1.0 mm Min (.039")	175 ± 0.1 mm (.069 ± .004")	3.5 ± 0.5 mm (.138 ± .002")	2.4 mm Max (.094")	4.0 ± 0.1 mm (.157 ± .004")	4.0 ± 0.1 mm (.157 ± .004")	2.0 ± 0.50 mm (.079 ± .002")	25 mm (.98")	0.400 mm (.016")	8.0 ± .30 mm (.315 ± .012")
12 mm	8.2 mm (.323")		1.5 mm Min (.060")		5.5 ± 0.5 mm (217 ± .002")	4.5 mm Max (.177")	4.0 ± 0.1 mm (.157 ± .004") 8.0 ± .01 mm (.315 ± .004")			30 mm (1.18")		12 ± .30 mm (.470 ± .012")
16 mm	12.1 mm (.476")				7.5 ± 0.10 mm (.295 ± .004")	6.5 mm (.256")	4.0 ± 0.1 mm (.157 ± .004") 8.0 ± .01 mm (.315 ± .004") 12.0 ± .004 mm (.472 ± .004")		2.0 ± .010 mm (.079 ± .004")	40 mm (1.575")		16 ± .30 mm (.630 ± .012")

Metric Dimensions Govern — English are in parentheses for reference only.

NOTE 1: A_0, B_0, and K_0 are determined by component size. The clearance between the components and the cavity must be within .05 min. to .50 max., the component cannot rotate more than 10° within the determined cavity.

REEL DIMENSIONS

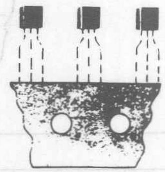
Metric Dimensions Govern — English are in Parentheses for Reference only.



Size	A Max	G	T Max
8 mm	330 mm (12.992")	8.4 mm + 1.5 mm, − 0.0 (.33" + .059", − 0.00)	14.4 mm (.56")
12 mm	330 mm (12.992")	12.4 mm + 2.0 mm, − 0.0 (.49" + .079", − 0.00)	18.4 mm (.72")
16 mm	360 mm (14.173")	16.4 mm + 2.0 mm, − 0.00 (.646" + .078", − 0.00)	22.4 mm (.882")

or Ammo Pack

RADIAL TAPE REEL OR AMMO PACK



Radial tape reel and ammo pack of the reliable TO-92 package are the best methods of capturing devices for automatic insertion in printed circuit boards. These methods of taping are compatible with various equipment for active and passive component insertion.

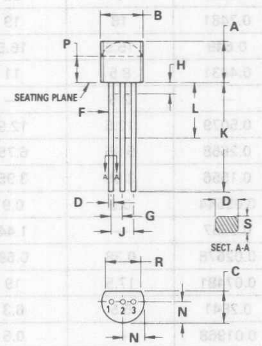
- Available on 360 mm Reels
- Available in Ammo Pack (Fan Fold Box)
- Accommodates Various Inserters
- Allows Flexible Circuit Board Layout
- 2.5 mm Pin Spacing For Soldering
- Conforms to EIA ACP Standard 1375 (RS-468)

Ordering Notes:

When ordering radial tape on reel or in ammo pack, specify the style per Figures 3 thru 8. Add the suffix "RLR" and "Style" to the device title, i.e. MPS3904RLRA. This will be a standard MPS3904 radial taped and supplied on a reel per Figure 3.

Reel Information — Minimum order quantity 1 Reel/$200LL.
Order in increments of 2000.

Ammo Pack Information — Minimum order quantity 1 Box/$200LL.
Order in increments of 2000.



NOTES:
1. CONTOUR OF PACKAGE BEYOND ZONE "P" IS UNCONTROLLED.
2. DIM "F" APPLIES BETWEEN "H" AND "L". DIM "D" & "S" APPLIES BETWEEN "L" & 12.70mm (0.5") FROM SEATING PLANE. LEAD DIM IS UNCONTROLLED IN "H" & BEYOND 12.70mm (0.5") FROM SEATING PLANE.
3. CONTROLLING DIM: INCH.

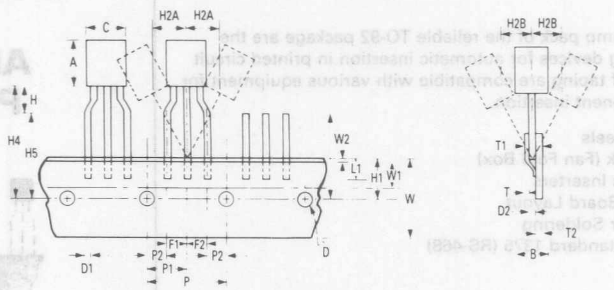
DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	4.32	5.33	0.170	0.210
B	4.45	5.20	0.175	0.205
C	3.18	4.19	0.125	0.165
D	0.41	0.55	0.016	0.022
F	0.41	0.48	0.016	0.019
G	1.15	1.39	0.045	0.055
H	—	2.54	—	0.100
J	2.42	2.66	0.095	0.105
K	12.70	—	0.500	—
L	6.35	—	0.250	—
N	2.04	2.66	0.080	0.105
P	2.93	—	0.115	—
R	3.43	—	0.135	—
S	0.39	0.50	0.015	0.020

CASE 29-04
TO-226AC
(TO-92)

7

TO-92 EIA RADIAL TAPE REEL OR AMMO PACK

Figure 1. Device Positioning on Tape

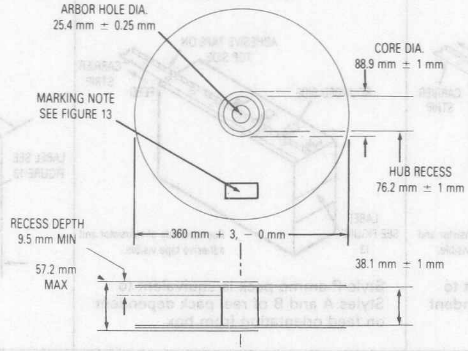


Symbol	Item	Specification			
		Inches		Millimeter	
		Min	Max	Min	Max
A	Component Body Height	0.170	0.210	4.32	5.33
B	Component Body Width	0.125	0.165	3.18	4.19
C	Component Body Length along Tape	0.1748	0.2052	4.44	5.21
D	Tape Feedhole Diameter	0.145	0.1693	3.7	4.3
D1	Component Lead Width Dimension	0.016	0.022	0.41	0.56
D2	Component Lead Thickness Dimension	0.015	0.020	0.38	0.51
F1, F2	Component Lead Pitch	0.0945	0.110	2.4	2.8
H	Bottom of Component to Seating Plane	0	0.0985	0	2.5
H1	Feedhole Location	0.3346	0.3741	8.5	9.5
H2A	Deflection Left or Right	0	0.03937	0	1
H2B	Deflection Front or Rear	0	0.03150	0	0.8
H3	Feedhole to Overall Component Height	0	1.2600	0	32
H4	Feedhole to Bottom of Component	0.7086	0.7481	18	19
H5	Feedhole to Seating Plane	0.610	0.649	15.5	16.5
L	Defective Unit Clipped Dimension	0.3346	0.4431	8.5	11
L1	Lead Wire Enclosure	0.09842	—	2.5	—
P	Feedhole Pitch	0.4921	0.5079	12.5	12.9
P1	Feedhole Component Center to Center	0.2342	0.2658	5.95	6.75
P2	First Lead Spacing Dimension	0.1397	0.1556	3.55	3.95
T	Adhesive Tape Thickness	0.0196	0.03544	0.5	0.9
T1	Overall Taped Package Thickness	—	0.0567	—	1.44
T2	Carrier Strip Thickness	0.01496	0.02678	0.38	0.68
W	Carrier Strip & Adhesive Tape Width	0.6889	0.07481	17.5	19
W1	Adhesive Tape Width	0.2165	0.2841	5.5	6.3
W2	Adhesive Tape Position	—	0.01968	—	0.5
B5	Lead Bend from Index Hole to Center Line	0.610	—	15.5	—

NOTES:
1. Maximum alignment deviation between leads not to be greater than 0.2 mm.
2. Defective components shall be clipped from the carrier tape such that the remaining protrusion (L) does not exceed a maximum of 11 mm.
3. Component lead to tape adhesion must meet the pull test requirements established in Figures 10, 11 and 12.
4. Maximum non-cumulative variation between tape feed holes shall not exceed 1 mm in 20 pitches.
5. Holddown tape not to extend beyond the edge(s) of carrier tape and there shall be no exposure of adhesive.
6. No more than 3 consecutive missing components is permitted.
7. A tape trailer, having at least three feed holes is required after the last component.
8. Splices shall not interfere with the sprocket feed holes.

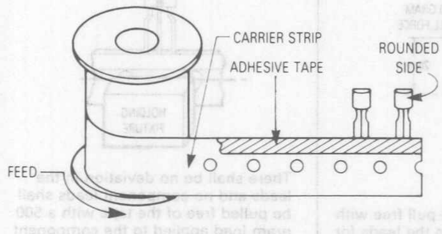
REEL STYLES

Figure 2. Reel Specifications



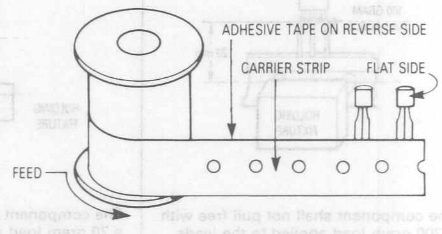
Material used must not cause deterioration of components or degrade lead solderability.

Figure 3. Style A



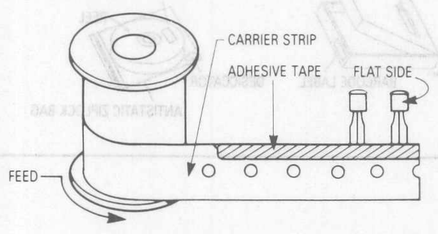
Rounded size of transistor and adhesive tape visible.

Figure 4. Style B



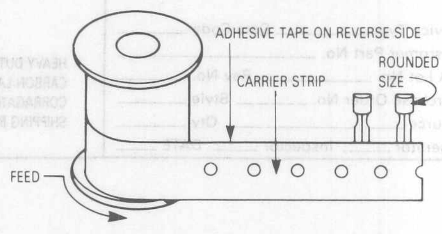
Flat side of transistor and carrier strip visible (adhesive tape on reverse side).

Figure 5. Style E



Flat side of transistor and adhesive tape visible.

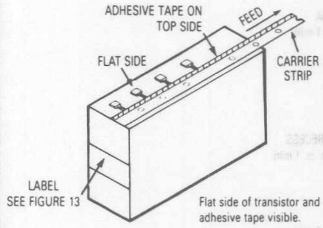
Figure 6. Style F



Rounded side of transistor and carrier strip visible (adhesive tape on reverse side).

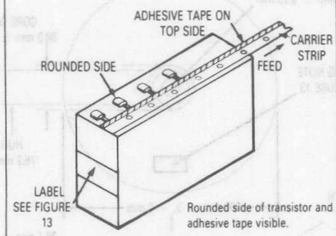
AMMO PACK STYLES

Figure 7. Style M



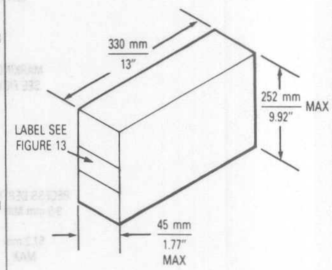
Style M ammo pack is equivalent to Styles E and F of reel pack dependent on feed orientation from box.

Figure 8. Style P



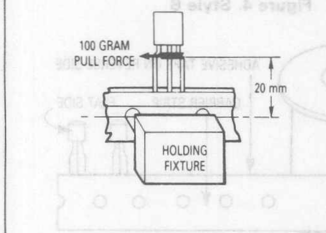
Style P ammo pack is equivalent to Styles A and B of reel pack dependent on feed orientation from box.

Figure 9. Ammo Pack Dimensions



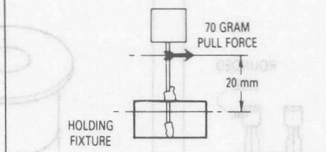
ADHESION PULL TESTS

Figure 10. Test #1



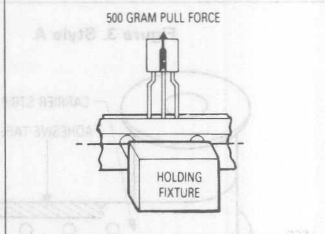
The component shall not pull free with a 300 gram load applied to the leads for 3 ± 1 second.

Figure 11. Test #2



The component shall not pull free with a 70 gram load applied to the leads for 3 ± 1 second.

Figure 12. Test #3

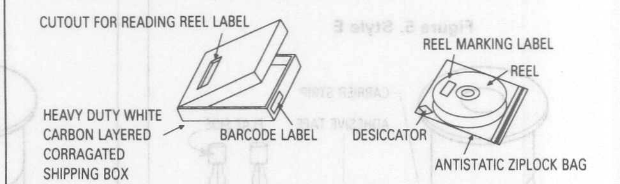


There shall be no deviation in the leads and no component leads shall be pulled free of the tape with a 500 gram load applied to the component body for 3 ± 1 second.

Figure 13. Marking for Reel/Ammo Pack

Device Type ______ Date Code ______
Customer Part No. ______
QA Lot No. ______ Rev No. ______
Purchase Order No. ______ Style ______
Source ______ Qty ______
Operator ______ Inspector ______ DATE ______

Figure 14. TO-92 Tape and Reel Shipping Container



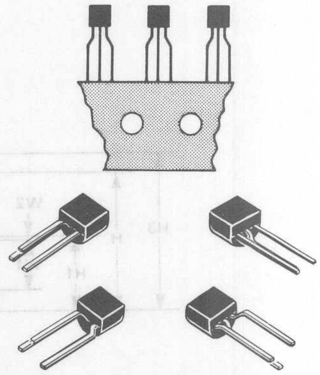
Radial tape reel and ammo pack of the reliable TO-92 package are the best methods of capturing devices for automatic insertion in printed circuit boards. These methods of taping are compatible with various equipment for active and passive component insertion.

- Available on 365 mm Reels
- Available in Ammo Pack (Fan Fold Box)
- Accommodates Various Inserters
- Allows Flexible Circuit Board Layout
- 2.5 mm Pin Spacing for Soldering
- Conforms to EIA ACP Standard 1375 (RS-468)*

*EIA ACP reel diameter 360 mm. Motorola is 365 mm.

When ordering radial type ON REEL specify the style per Figure 4. Add the suffix to the device title, i.e. BC237ARL1. This will be a standard BC237A radial taped and supplied on a reel per RL1 option.

and Lead Forming

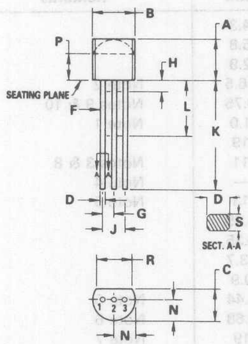


TO-92 Lead Forming

Lead configurations conform to TO-18 or TO-5 pin circles.

Ordering Notes:

Ammo Pack and Reel information — **order in increments of 2000.**
When ordering Lead Formed TO-92, verify the style per Figure 8.



NOTES:
1. CONTOUR OF PACKAGE BEYOND ZONE "P" IS UNCONTROLLED.
2. DIM "F" APPLIES BETWEEN "H" AND "L". DIM "D" & "S" APPLIES BETWEEN "L" & 12.70mm (0.5") FROM SEATING PLANE. LEAD DIM IS UNCONTROLLED IN "H" & BEYOND 12.70mm (0.5") FROM SEATING PLANE.
3. CONTROLLING DIM: INCH.

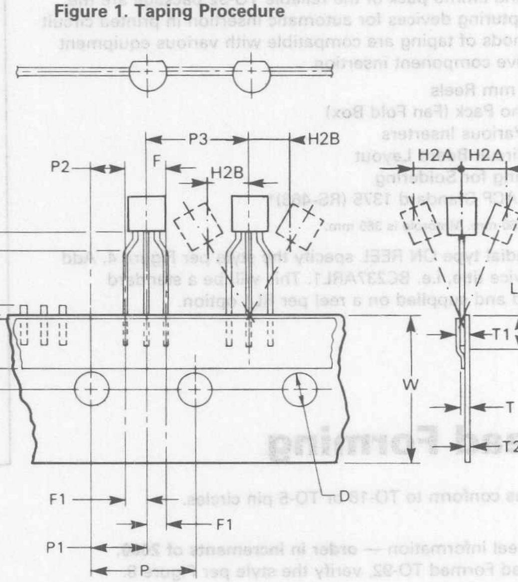
CASE 29-04
TO-226AC
(TO-92)

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.32	5.33	0.170	0.210
B	4.45	5.20	0.175	0.205
C	3.18	4.19	0.125	0.165
D	0.41	0.55	0.016	0.022
F	0.41	0.48	0.016	0.019
G	1.15	1.39	0.045	0.055
H	—	2.54	—	0.100
J	2.42	2.66	0.095	0.105
K	12.70	—	0.500	—
L	6.35	—	0.250	—
N	2.04	2.66	0.080	0.105
P	2.93	—	0.115	—
R	3.43	—	0.135	—
S	0.39	0.50	0.015	0.020

7

TO-92 TAPE REEL AND LEAD FORMING

Figure 1. Taping Procedure



7

Symbol	Item	Specification		Remarks
		Min mm	Max mm	
D	Tape Feed Hole Diameter	3.7	4.3	
F	Overall Component Lead Pitch	4.8	5.8	
F1	Component Lead Pitch	2.4	2.9	
H	Height of Seating Plane	15.5	16.5	Note 2
H1	Feed Hole Location	8.5	9.75	Notes 9 & 10
H2A, B	Deflection Front or Rear, Left or Right	0	1.0	Note 1
H3	Feed Hole to Bottom of Component	18	19	
L	Lead Length After Component Removal	0	11	Notes 3 & 8
L1	Lead Wire Enclosure	2.5	—	Note 4
P	Feed Hole Pitch	12.4	13	Note 5
P1	Feed Hole — Component Centre Distance	5.95	6.75	
P2	Feed Hole — First Lead Distance	3.02	4.35	
P3	Component Centre Pitch	11.7	13.7	
T	Total Tape Thickness	0.5	0.9	
T1	Overall Taped Package Thickness	—	1.44	Note 6
T2	Carrier Tape Thickness	0.38	0.68	Note 6
W	Overall Tape Width	17.5	19	Note 7
W1	Holddown Tape Width	5.7	6.3	Note 7
W2	Holddown Tape Position	0	0.5	Note 7

Notes:
1. Maximum alignment deviation between leads not to be greater than 0.2 mm.
2. As illustrated, the clearance to the lead standoff form shall be defined to the point of radius for the standoff form.
3. Defective components shall be clipped from the carrier tape such that the remaining protrusion (L) does not exceed a maximum of 11 mm.
4. Component lead to tape adhesion must meet the pull test requirements established in Figures 4, 5 and 6.
5. Maximum non-cumulative variation between tape and feed holes shall not exceed 1.0 mm in 20 pitches.
6. Overall taped package thickness, including component leads and tape splices shall not exceed 1.44 mm.
7. Holddown tape not to extend beyond the edge(s) of carrier tape and there shall be no exposure of adhesive.
8. No more than 3 consecutive missing components is permitted.
9. A tape trailer having at least three feed holes is required after the last component.
10. Splices shall not interfere with the sprocket feed holes.

Figure 2. REEL Pack Dimensions

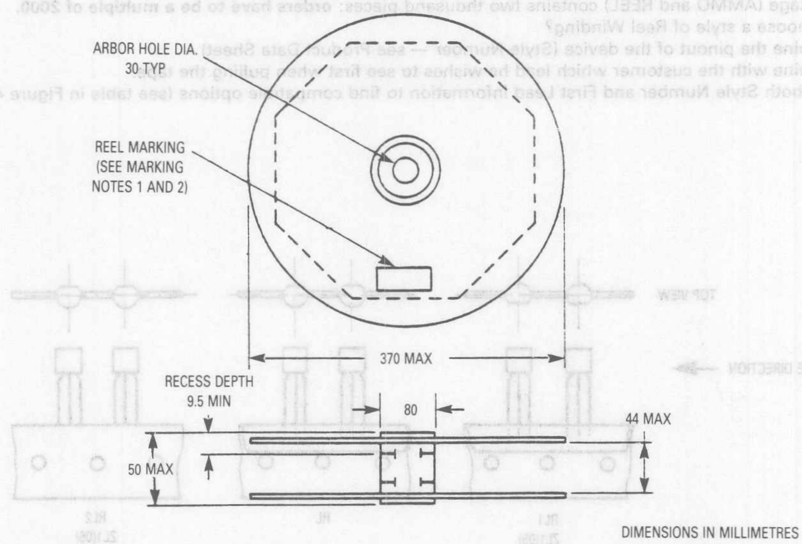


Figure 3. AMMO Pack Dimensions (Dimensions in mm)

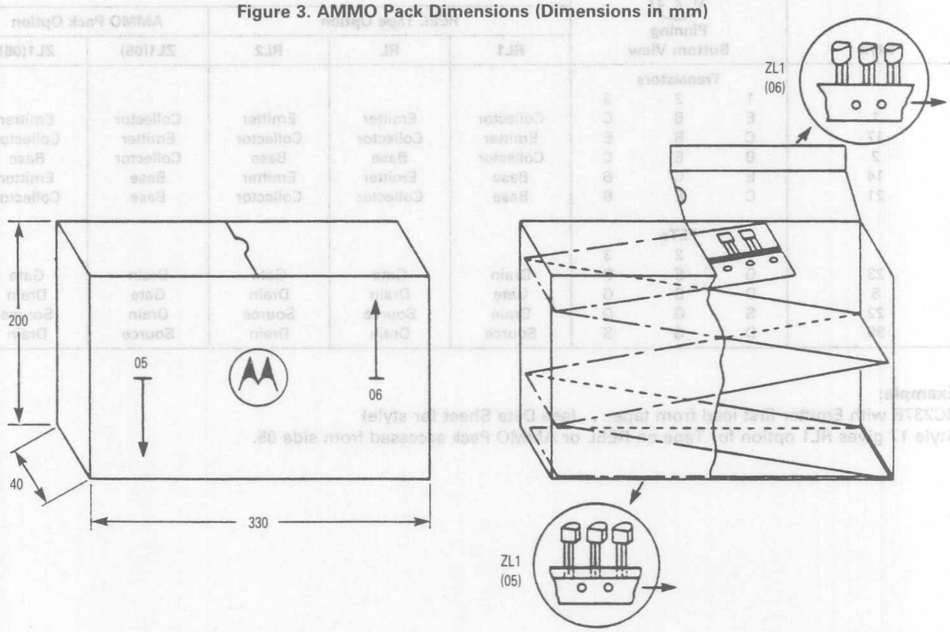
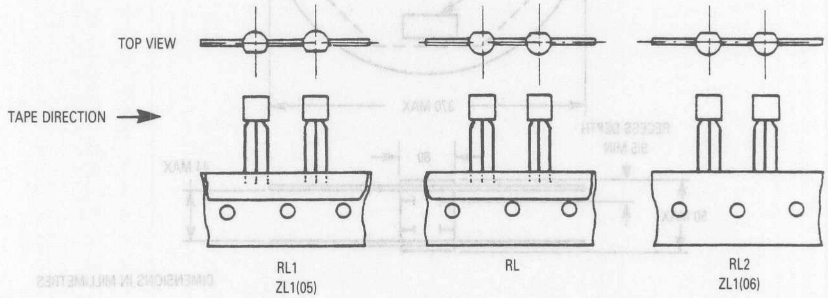


Figure 4. Ordering Notes

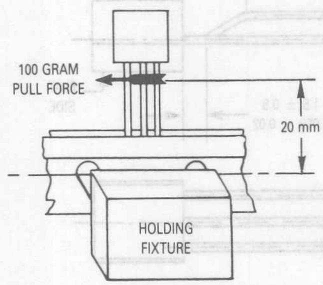
1. Each package (AMMO and REEL) contains two thousand pieces: **orders have to be a multiple of 2000.**
2. How to choose a style of Reel Winding?
   — Determine the pinout of the device (Style Number — see Product Data Sheet)
   — Determine with the customer which lead he wishes to see first when pulling the tape.
   — Match both Style Number and First Lead information to find compatible options (see table in Figure 4).



Style	1 2 3 Pinning Bottom View			First Lead Seen				
				REEL Tape Option			AMMO Pack Option	
				RL1	RL	RL2	ZL1(05)	ZL1(06)
	Transistors							
	1	2	3					
1	E	B	C	Collector	Emitter	Emitter	Collector	Emitter
17	C	B	E	Emitter	Collector	Collector	Emitter	Collector
2	B	E	C	Collector	Base	Base	Collector	Base
14	E	C	B	Base	Emitter	Emitter	Base	Emitter
21	C	E	B	Base	Collector	Collector	Base	Collector
	FETs							
	1	2	3					
23	G	S	D	Drain	Gate	Gate	Drain	Gate
5	D	S	G	Gate	Drain	Drain	Gate	Drain
22	S	G	D	Drain	Source	Source	Drain	Source
30	D	G	S	Source	Drain	Drain	Source	Drain

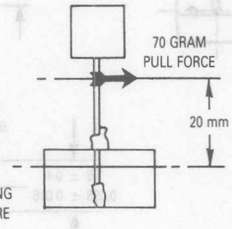
Example:
BC237B with Emitter first lead from tape . . . (see Data Sheet for style)
Style 17 gives RL1 option for Tape on REEL or AMMO Pack accessed from side 05.

Figure 5. Adhesion Pull Test



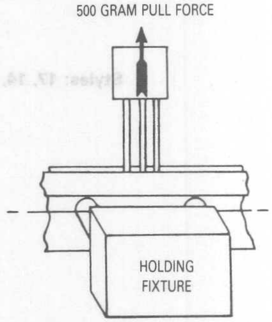
The component shall not pull free with a 300 gram load applied to the leads for 3 ± 1 second.

Figure 6. Adhesion Pull Test No. 2



The component shall not pull free with a 70 gram load applied to the leads for 3 ± 1 second.

Figure 7. Adhesion Pull Test No. 3



There shall be no deviation in the leads and no component leads shall be pulled free of the tape with a 500 gram load applied to the component body for 3 ± 1 second.

Marking Notes:

1. Minimum container and reel marking shall consist of the following items:
   a. Motorola
   b. Customer Purchase Order Number
   c. Quantity
   d. Date of Reeling
   e. Motorola Part Number
2. Where applicable, the following items will be included:
   a. Customer Part Number
   b. Device Date Code

TO-92 LEAD FORMING

Figure 8. Ordering Notes

How to choose Lead Form option:

1. Determine option either TO-18 or TO-5, see Dimensional Drawings
   *Identify measurement between centres of the two outside leads:
   i.e. 2.5 mm for TO-18
   5.0 mm for TO-5
2. Determine the pinout of the device (Style Number — see Product Data Sheet)
3. Identify Drawing corresponding to Style Number (see Figures 8a and 8b).

Example:
BC237B configured TO-18. . . .
See Data Sheet for Style Number
Style 17 . . . Drawing indicates Dimensions, and that position of Centre Lead is towards the round side of the product (towards the back)
Order type: **BC237B18**

Other Examples:

P2N2222-18	P2N2222A18
2N5551-5	BC488A18
BC337-25-5	BC547C5

Note: For reverse configurations, please consult the factory.

Figure 8a. TO-18 Styles and Dimensions

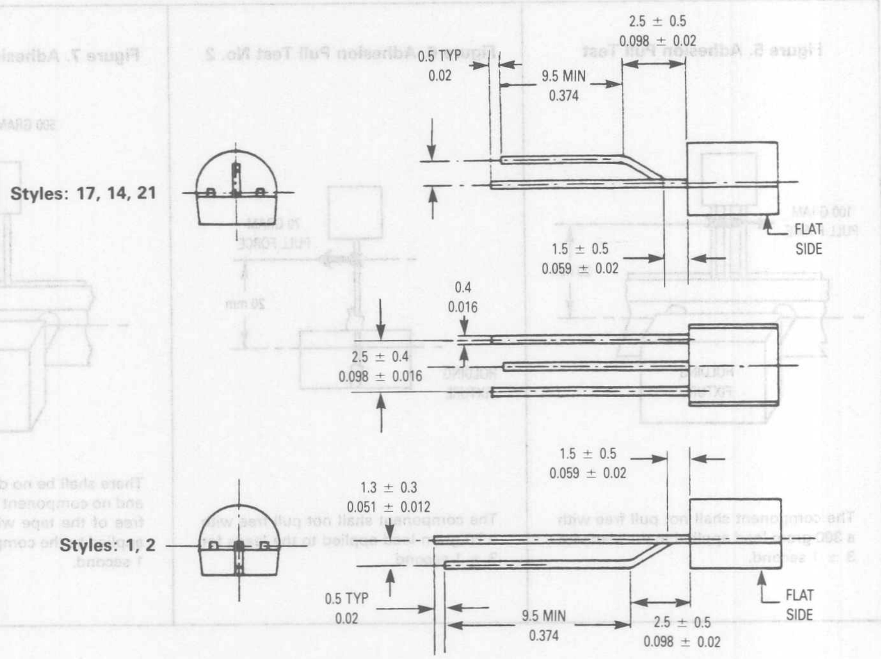
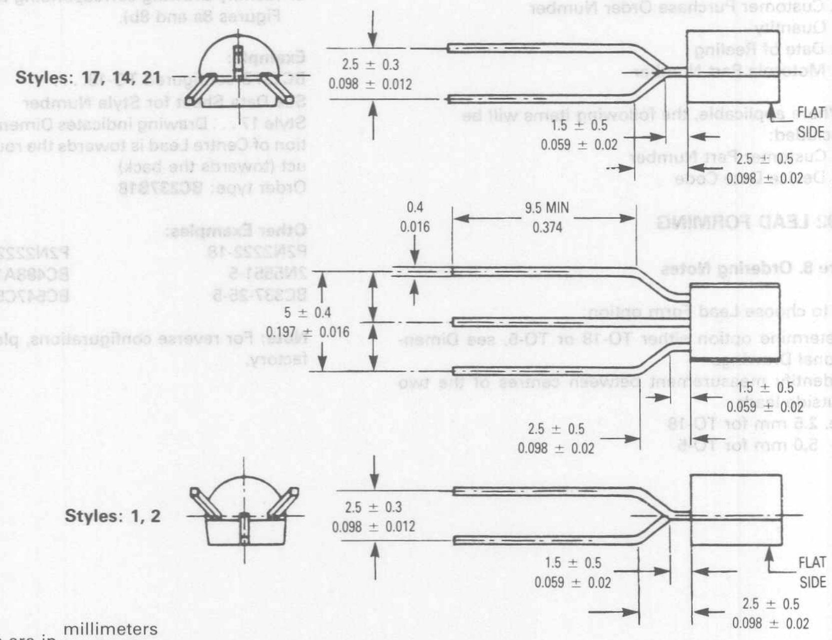
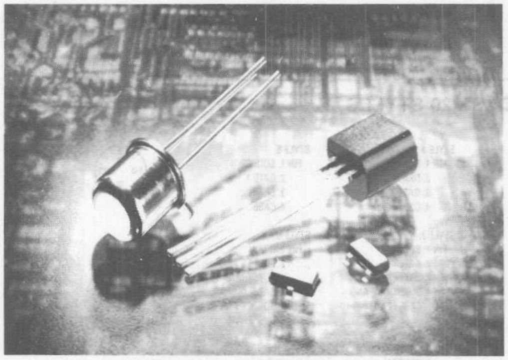


Figure 8b. TO-5 Styles and Dimensions



Dimensions are in $\frac{\text{millimeters}}{\text{inches}}$



The following pages contain information on the various packages referenced on the individual data sheets. Information includes: a picture of the package, dimensions in both millimeters and inches, the various pinout configurations (styles), a cross reference for Case numbers, "old" JEDEC "TO" numbers, and the new JEDEC "TO" designation.

Additionally, abstracts of available application notes are provided. Please contact your local sales representative for those desired.

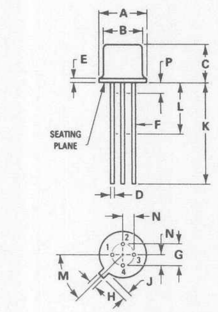
Package Outline Dimensions and Application Literature

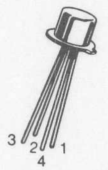
8

Package Outline Dimensions

Dimensions are in inches unless otherwise noted.

CASE 20-03 TO-206AF (TO-72) METAL





NOTE: ALL RULES AND NOTES ASSOCIATED WITH TO-72 OUTLINE SHALL APPLY.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.31	5.84	0.209	0.230
B	4.52	4.95	0.178	0.195
C	4.32	5.33	0.170	0.210
D	0.41	0.53	0.016	0.021
E	—	0.76	—	0.030
F	0.41	0.48	0.016	0.019
G	2.54 BSC		0.100 BSC	
H	0.91	1.17	0.036	0.046
J	0.71	1.22	0.028	0.048
K	12.70	—	0.500	—
L	6.35	—	0.250	—
M	45° BSC		45° BSC	
N	1.27 BSC		0.050 BSC	
P	—	1.27	—	0.050

All JEDEC dimensions and notes apply.

CASE 20 STYLES

STYLE 1:
PIN 1. SOURCE
2. DRAIN
3. GATE
4. CASE LEAD

STYLE 2:
PIN 1. SOURCE
2. GATE
3. DRAIN
4. SUBSTRATE AND CASE LEAD

STYLE 3:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. CASE LEAD

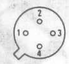
STYLE 4:
PIN 1. SOURCE
2. GATE
3. DRAIN
4. GATE 2 — SUBSTRATE AND CASE

STYLE 5:
PIN 1. SOURCE
2. GATE 1
3. DRAIN
4. CASE

STYLE 6:
PIN 1. DRAIN
2. SOURCE AND SUBSTRATE
3. GATE
4. SOURCE AND SUBSTRATE

STYLE 7:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. CASE AND SUBSTRATE

STYLE 8:
PIN 1. EMITTER 2
2. BASE 1
3. COLLECTOR
4. EMITTER 1 BASE 2

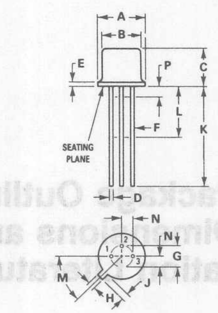


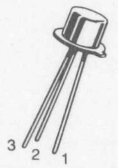
STYLE 9:
PIN 1. DRAIN
2. GATE 2
3. GATE 1
4. SOURCE, SUBSTRATE AND CASE

STYLE 10:
PIN 1. EMITTER
2. BASE
3. COLLECTOR
4. CASE

STYLE 11:
PIN 1. EMITTER
2. CATHODE
3. COLLECTOR
4. ANODE

CASE 22-03 TO-206AA (TO-18) METAL





DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.31	5.84	0.209	0.230
B	4.52	4.95	0.178	0.195
C	4.32	5.33	0.170	0.210
D	0.406	0.533	0.016	0.021
E	—	0.762	—	0.030
F	0.406	0.483	0.016	0.019
G	2.54 BSC		0.100 BSC	
H	0.914	1.17	0.036	0.046
J	0.711	1.22	0.028	0.048
K	12.70	—	0.500	—
L	6.35	—	0.250	—
M	45° BSC		45° BSC	
N	1.27 BSC		0.050 BSC	
P	—	1.27	—	0.050

All JEDEC notes and dimensions apply.

CASE 22 STYLES

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 2:
PIN 1. SOURCE, SUBSTRATE AND CASE
2. GATE
3. DRAIN

STYLE 3:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 4:
PIN 1. SOURCE
2. DRAIN
3. GATE AND CASE

STYLE 5:
PIN 1. EMITTER
2. BASE 1
3. BASE 2

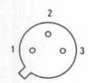
STYLE 6:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 7:
PIN 1. ANODE
2. BASE
3. CATHODE

STYLE 8:
PIN 1. GATE
2. ANODE 1
3. ANODE 2

STYLE 9:
PIN 1. ANODE 2
2. ANODE 1
3. GATE (CONNECTED TO CASE)

STYLE 10:
PIN 1. BASE
2. EMITTER
3. BASE



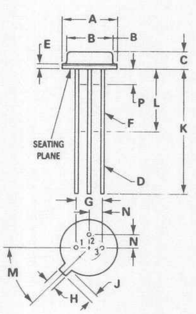
STYLE 11:
PIN 1. DRAIN
2. SOURCE, SUBSTRATE

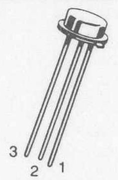
STYLE 12:
PIN 1. SOURCE
2. GATE
3. DRAIN (CASE)

STYLE 13:
PIN 1. ANODE
2. GATE
3. CATHODE

CASE 26-03 TO-206AB (TO-46) METAL

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

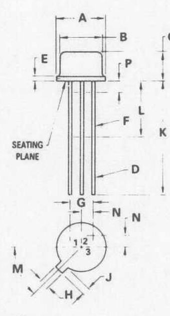




DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.31	5.84	0.209	0.230
B	4.52	4.95	0.178	0.195
C	1.65	2.16	0.065	0.085
D	0.406	0.533	0.016	0.021
E	—	1.02	—	0.040
F	0.305	0.483	0.012	0.019
G	2.54 BSC		0.100 BSC	
H	0.914	1.17	0.036	0.046
J	0.711	1.22	0.028	0.048
K	12.70	—	0.500	—
L	6.35	—	0.250	—
M	45° BSC		45° BSC	
N	1.27 BSC		0.050 BSC	
P	—	1.27	—	0.050

All JEDEC dimensions and notes apply.

CASE 27-02 TO-206AC (TO-52) METAL



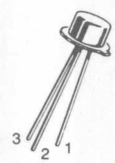
STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 2:
PIN 1. DRAIN
2. SOURCE
3. GATE & CASE

STYLE 3:
PIN 1. EMITTER
2. BASE
3. BASE 2

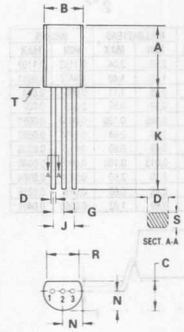
STYLE 4:
PIN 1. SOURCE
2. DRAIN
3. GATE & CASE

STYLE 5:
PIN 1. SOURCE
2. GATE
3. DRAIN & CASE

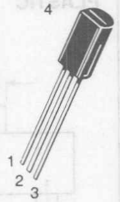


DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.31	5.84	0.209	0.230
B	4.52	4.95	0.178	0.195
C	2.92	3.81	0.115	0.150
D	—	0.533	—	0.021
E	—	0.762	—	0.030
F	0.406	0.483	0.016	0.019
G	2.54 BSC		0.100 BSC	
H	0.914	1.17	0.036	0.046
J	0.711	1.22	0.028	0.048
K	12.70	—	0.500	—
L	6.35	—	0.250	—
M	45° BSC		45° BSC	
N	1.27 BSC		0.050 BSC	
P	—	1.27	—	0.050

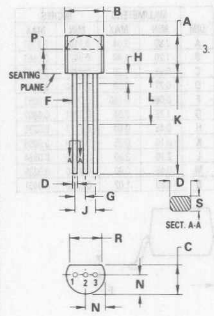
NOTE:
1. ALL RULES & NOTES ASSOCIATED WITH TO-52 OUTLINE SHALL APPLY.



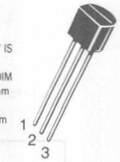
NOTES:
1. DIMENSIONS -A- AND -B- ARE DATUMS.
2. -T- IS SEATING PLANE.
3. POSITIONAL TOLERANCE FOR LEADS:
   | ⌖ | ϕ 0.10 (0.004) Ⓜ | T | A Ⓜ | B Ⓜ |
4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1982.
5. CONTROLLING DIM: INCH.



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	7.37	7.87	0.290	0.310
B	4.44	5.21	0.175	0.205
C	3.18	4.19	0.125	0.165
D	0.46	0.61	0.018	0.024
G	1.27 BSC		0.050 BSC	
J	2.54 BSC		0.100 BSC	
K	12.70	—	0.500	—
N	2.03	2.92	0.080	0.115
R	3.43	—	0.135	—
S	0.46	0.61	0.018	0.024



NOTES:
1. CONTOUR OF PACKAGE BEYOND ZONE "P" IS UNCONTROLLED.
2. DIM "F" APPLIES BETWEEN "H" AND "L". DIM "D" & "S" APPLIES BETWEEN "L" & 12.70mm (0.5") FROM SEATING PLANE. LEAD DIM IS UNCONTROLLED IN "H" & BEYOND 12.70mm (0.5") FROM SEATING PLANE.
3. CONTROLLING DIM: INCH.



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	4.32	5.33	0.170	0.210
B	4.45	5.20	0.175	0.205
C	3.18	4.19	0.125	0.165
D	0.41	0.55	0.016	0.022
F	0.41	0.48	0.016	0.019
G	1.15	1.39	0.045	0.055
H	—	2.54	—	0.100
J	2.42	2.66	0.095	0.105
K	12.70	—	0.500	—
L	6.35	—	0.250	—
N	2.04	2.66	0.080	0.105
P	2.93	—	0.115	—
R	3.43	—	0.135	—
S	0.39	0.50	0.015	0.020

CASE 29 STYLES

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMMITTER
3. COLLECTOR

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 6:
PIN 1. GATE
2. SOURCE & SUBSTRATE
3. DRAIN

STYLE 7:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 8:
PIN 1. DRAIN
2. GATE
3. SOURCE & SUBSTRATE

STYLE 9:
PIN 1. BASE 1
2. EMITTER
3. BASE 2

STYLE 10:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 11:
PIN 1. ANODE
2. CATHODE & ANODE
3. CATHODE

STYLE 12:
PIN 1. MAIN TER 1
2. GATE
3. MAIN TER 2

STYLE 13:
PIN 1. ANODE 1
2. GATE
3. CATHODE 2

STYLE 14:
PIN 1. EMITTER
2. COLLECTOR
3. BASE

STYLE 15:
PIN 1. ANODE 1
2. CATHODE
3. ANODE 2

STYLE 16:
PIN 1. ANODE
2. GATE
3. CATHODE

STYLE 17:
PIN 1. COLLECTOR
2. BASE
3. EMITTER

STYLE 18:
PIN 1. ANODE
2. CATHODE
3. NOT CONN

STYLE 19:
PIN 1. GATE
2. ANODE
3. CATHODE

STYLE 20:
PIN 1. NOT CONN
2. CATHODE
3. ANODE

STYLE 21:
PIN 1. COLLECTOR
2. EMITTER
3. BASE

STYLE 22:
PIN 1. SOURCE
2. GATE
3. DRAIN

STYLE 23:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 24:
PIN 1. EMITTER
2. COLLECTOR ANODE
3. CATHODE

STYLE 25:
PIN 1. MT 1
2. GATE
3. MT 2

STYLE 26:
PIN 1. V_{CC}
2. GROUND
3. OUTPUT

STYLE 27:
PIN 1. MT
2. SUBSTRATE
3. MT

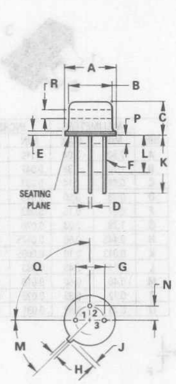
STYLE 28:
PIN 1. CATHODE
2. ANODE
3. GATE

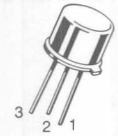
STYLE 29:
PIN 1. NOT CONN
2. ANODE
3. CATHODE

STYLE 30:
PIN 1. DRAIN
2. GATE
3. SOURCE

STYLE 31:
PIN 1. GATE
2. DRAIN
3. SOURCE

CASE 79-02 TO-205AD (TO-39) METAL

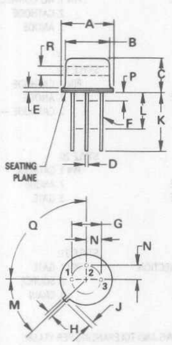


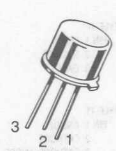


DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	8.89	9.40	0.350	0.370
B	8.00	8.51	0.315	0.335
C	6.10	6.60	0.240	0.260
D	0.406	0.533	0.016	0.021
E	0.229	3.18	0.009	0.125
F	0.406	0.483	0.016	0.019
G	4.83	5.33	0.190	0.210
H	0.711	0.864	0.028	0.034
J	0.737	1.02	0.029	0.040
K	12.70	—	0.500	—
L	6.35	—	0.250	—
M	45° NOM		45° NOM	
P	—	1.27	—	0.050
Q	90° NOM		90° NOM	
R	2.54	—	0.100	—

All JEDEC Dimensions and Notes Apply.

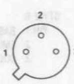
CASE 79-03 TO-206AF (TO-39) METAL





DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	9.02	9.30	0.355	0.366
B	8.00	8.51	0.315	0.335
C	4.19	4.57	0.165	0.180
D	0.43	0.53	0.017	0.021
E	0.43	0.89	0.017	0.035
F	0.41	0.48	0.016	0.019
G	4.83	5.33	0.190	0.210
H	0.71	0.86	0.028	0.034
J	0.74	1.02	0.029	0.040
K	12.70	—	0.500	—
M	45°NOM		45°NOM	
N	2.54 TYP		0.100 TYP	
Q	90° NOM		90° NOM	

CASE 79 STYLES



NOTE:
1. ALL RULES AND NOTES ASSOCIATED WITH TO-39 OUTLINE SHALL APPLY.

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 2:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 3:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 4:
PIN 1. MAIN TERM. 1
2. GATE
3. MAIN TERM. 2

STYLE 5:
PIN 1. COLLECTOR
2. BASE
3. EMITTER

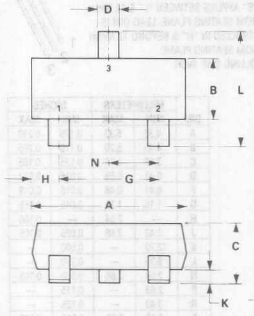
STYLE 6:
PIN 1. SOURCE
2. GATE
3. DRAIN (CASE)

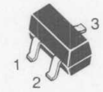
STYLE 7:
PIN 1. DRAIN
2. GATE
3. SOURCE

STYLE 8:
PIN 1. ANODE
2. ANODE
3. CATHODE

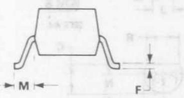
STYLE 9:
PIN 1. SOURCE
2. DRAIN
3. GATE

CASE 318-02 TO-236AA (SOT-23) PLASTIC

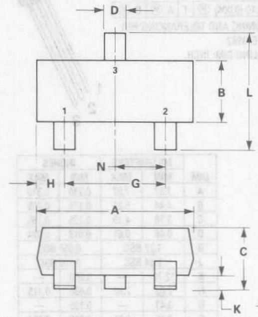


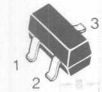


DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	2.80	3.04	0.1102	0.1197
B	1.20	1.40	0.0472	0.0551
C	0.85	1.20	0.033	0.0472
D	0.37	0.50	0.0150	0.020
F	0.085	0.130	0.0034	0.0051
G	1.78	2.04	0.0701	0.0807
H	0.45	0.60	0.0177	0.0236
K	0.10	0.25	0.0040	0.0098
L	2.10	2.50	0.0830	0.0984
M	0.45	0.60	0.0180	0.0236
N	0.89	1.02	0.0350	0.0401

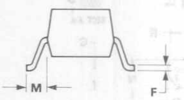


CASE 318-03 TO-236AB (SOT-23) LOW PROFILE PLASTIC

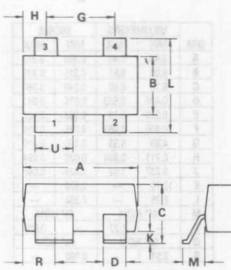


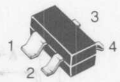


DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	2.80	3.04	0.1102	0.1197
B	1.20	1.40	0.0472	0.0551
C	0.89	1.11	0.035	0.044
D	0.37	0.50	0.015	0.020
F	0.085	0.130	0.0034	0.0051
G	1.78	2.04	0.0701	0.0807
H	0.45	0.60	0.0177	0.0236
K	0.013	0.100	0.0005	0.0040
L	2.10	2.50	0.0830	0.0984
M	0.45	0.60	0.018	0.0236
N	0.89	1.02	0.0350	0.0401

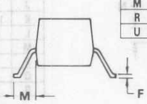


CASE 318A-04 (SOT-143) LOW PROFILE PLASTIC

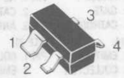


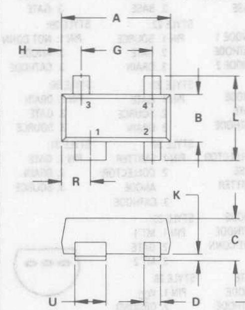


DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	2.80	3.04	0.110	0.120
B	1.20	1.39	0.047	0.055
C	0.84	1.14	0.033	0.045
D	0.38	0.50	0.015	0.020
F	0.07	0.15	0.003	0.006
G	1.78	2.03	0.070	0.080
H	0.445	0.60	0.0175	0.024
K	0.013	0.10	0.0005	0.004
L	2.11	2.48	0.083	0.098
M	0.46	0.60	0.018	0.024
R	0.72	0.83	0.028	0.033
U	0.79	0.88	0.031	0.035

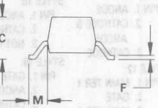


CASE 318B-03 (SOT-143) PLASTIC





DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	2.80	3.04	0.110	0.120
B	1.20	1.39	0.047	0.055
C	1.05	1.24	0.041	0.049
D	0.38	0.50	0.015	0.020
F	0.08	0.15	0.003	0.006
G	1.78	2.03	0.070	0.080
H	0.445	0.60	0.0175	0.024
K	0.10	0.25	0.004	0.010
L	2.11	2.48	0.083	0.098
M	0.46	0.60	0.018	0.024
R	0.71	0.83	0.028	0.033
U	0.79	0.88	0.031	0.035



CASE 318A,B STYLES

STYLE 1:
PIN 1. COLLECTOR
2. EMITTER
3. EMITTER
4. BASE

STYLE 2:
PIN 1. SOURCE
2. DRAIN
3. GATE 1
4. GATE 2

STYLE 3:
PIN 1. GROUND
2. SOURCE
3. INPUT
4. OUTPUT

STYLE 4:
PIN 1. OUTPUT
2. GROUND
3. GROUND
4. INPUT

STYLE 5:
PIN 1. SOURCE
2. DRAIN
3. GATE #1
4. SOURCE

CASE 318 STYLES

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

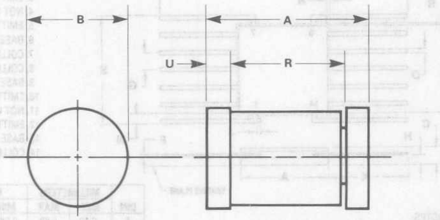
STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE — ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

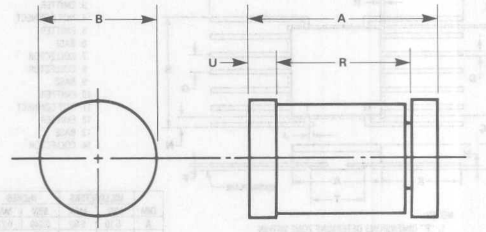
NOTES:
1. DIMENSIONING AND TOLERANCING PER Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

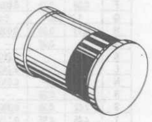
CASE 362-01 (MLL34)



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	3.30	3.70	0.130	0.146
B	1.60	1.70	0.063	0.067
R	2.49	2.59	0.098	0.102
U	0.41	0.55	0.016	0.022

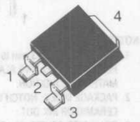
CASE 362B-01 (MLL41)

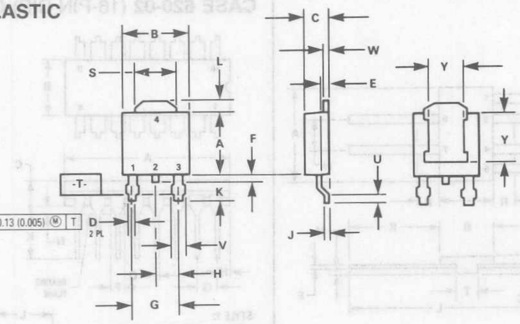




DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	4.80	5.20	0.189	0.205
B	2.39	2.59	0.094	0.102
R	3.68	4.54	0.145	0.179
U	0.30	0.55	0.012	0.022

CASE 369A-03 (DPAK) PLASTIC





NOTES:
1. SURFACE "T" IS BOTH A DATUM AND A MOUNTING SURFACE.
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
3. CONTROLLING DIMENSION: INCH.

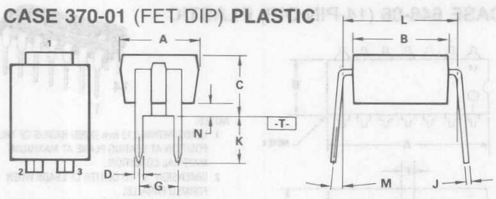
STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

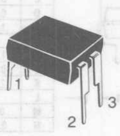
DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.97	6.22	0.235	0.245
B	6.35	6.73	0.250	0.265
C	2.19	2.38	0.086	0.094
D	0.69	0.88	0.027	0.035
E	0.97	1.06	0.038	0.042
F	0.64	0.88	0.025	0.035
G	4.58 BSC		0.180 BSC	
H	2.29 BSC		0.090 BSC	
J	6.46	0.58	0.018	0.023
K	2.59	2.89	0.102	0.114
L	0.89	1.27	0.035	0.050
S	5.21	5.46	0.205	0.215
U	0.51	—	0.020	—
V	0.77	1.14	0.030	0.045
W	0.84	0.94	0.033	0.037
Y	4.32	—	0.170	—

CASE 370-01 (FET DIP) PLASTIC



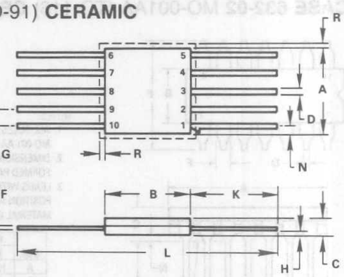
NOTES:
1. SURFACE "T" IS BOTH A DATUM AND SEATING PLANE.
2. POSITIONAL TOLERANCE FOR LEADS; D DIM 4 PL
   | ⌖ | 0.27 (.010) Ⓜ | -T- | A Ⓜ |
   LEADS; J DIM 4 PL
   | ⌖ | 0.27 (0.010) Ⓜ | -T- | B Ⓜ |
3. DIMENSIONING AND TOLERANCING PER Y14.5M, 1982.
4. CONTROLLING DIMENSION: INCH
5. DIMENSION "J" PRIOR TO SOLDER DIP PLATING

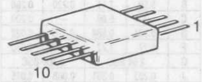
STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	4.70	5.02	0.185	0.198
B	6.10	7.11	0.240	0.280
C	4.06	5.08	0.160	0.200
D	0.38	0.63	0.015	0.025
G	2.54 BSC		0.100 BSC	
J	0.30	0.43	0.012	0.017
K	2.79	3.81	0.110	0.150
L	7.62 BSC		0.300 BSC	
M	0°	15°	0°	15°
N	0.51	1.77	0.020	0.070

CASE 606-04 (TO-91) CERAMIC

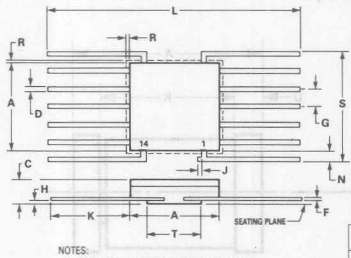




NOTE:
1. ALL RULES & NOTES ASSOCIATED WITH TO-91 OUTLINE SHALL APPLY.
2. LEADS WITHIN 0.25 mm (0.010) TOTAL OF TRUE POSITION AT MAXIMUM MATERIAL CONDITION (AT BODY)

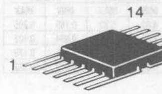
DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	6.10	7.36	0.240	0.290
B	6.10	6.60	0.240	0.260
C	0.762	1.77	0.030	0.070
D	0.254	0.482	0.010	0.019
F	0.077	0.152	0.003	0.006
G	1.15	1.39	0.045	0.055
H	0.127	0.889	0.005	0.035
K	1.78	—	0.070	—
R	—	0.381	—	0.015

8

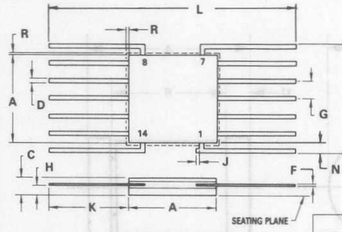


STYLE 1:
PIN 1. COLLECTOR
2. BASE
3. EMITTER
4. NOT CONNECT
5. EMITTER
6. BASE
7. COLLECTOR
8. COLLECTOR
9. BASE
10. EMITTER
11. NOT CONNECT
12. EMITTER
13. BASE
14. COLLECTOR

NOTES:
1. "R" DIMENSIONS DETERMINE ZONE WITHIN WHICH ALL BODY AND LEAD IRREGULARITIES LIE.
2. LEADS WITHIN 0.13 mm (0.005) TOTAL OF TRUE POSITION RELATIVE TO "A" AT MAXIMUM MATERIAL CONDITION.

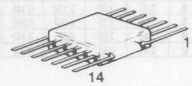


DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	6.10	6.98	0.240	0.275
C	0.76	1.77	0.030	0.070
D	0.25	0.48	0.010	0.019
F	0.08	0.15	0.003	0.006
G	1.27 BSC		0.050 BSC	
H	0.13	0.88	0.005	0.035
J	—	0.38	—	0.015
K	6.35	—	0.250	—
L	18.80	—	0.740	—
N	0.25	—	0.010	—
R	—	0.38	—	0.015
S	7.62	8.38	0.300	0.330
T	4.45	4.95	0.175	0.195



PIN 1. COLLECTOR
2. BASE
3. EMITTER
4. NOT CONNECTED
5. EMITTER
6. BASE
7. COLLECTOR
8. COLLECTOR
9. BASE
10. EMITTER
11. NOT CONNECTED
12. EMITTER
13. BASE
14. COLLECTOR

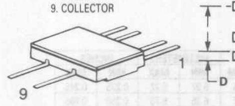
NOTES:
1. "R" DIMENSIONS DETERMINE ZONE WITHIN WHICH ALL BODY AND LEAD IRREGULARITIES LIE.
2. LEADS WITHIN 0.13 mm (0.005) TOTAL OF TRUE POSITION RELATIVE TO "A" AT MAXIMUM MATERIAL CONDITION.

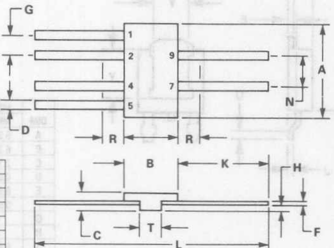


DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	6.10	6.60	0.240	0.260
C	0.76	1.78	0.030	0.070
D	0.33	0.48	0.013	0.019
F	0.08	0.15	0.003	0.006
G	1.27 BSC		0.050 BSC	
H	0.30	0.89	0.012	0.035
J	—	0.38	—	0.015
K	6.35	9.40	0.250	0.370
L	18.80	—	0.740	—
N	0.25	—	0.010	—
R	—	0.38	—	0.015
S	7.62	8.38	0.300	0.330

CASE 610A-04 CERAMIC

STYLE 1:
PIN 1. BASE
2. EMITTER
4. EMITTER
5. BASE
7. COLLECTOR
9. COLLECTOR

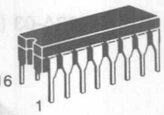


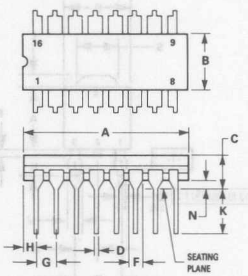


DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	6.10	7.37	0.240	0.290
B	2.92	4.06	0.115	0.160
C	0.76	2.03	0.030	0.070
D	0.36	0.48	0.014	0.019
F	0.08	0.15	0.003	0.006
G	1.27 BSC		0.050 BSC	
H	0.13	0.89	0.005	0.035
K	3.81	—	0.150	—
L	10.54	—	0.415	—
N	2.54 BSC		0.100 BSC	
R	—	1.27	—	0.050
T	1.65	2.03	0.065	0.080

NOTES:
1. DIM "D," "G" & "N" TO BE MEASURED IN ZONE "R."
2. LEADS WITHIN 0.13 mm (0.005) TOTAL OF TRUE POSITION WITHIN "R" AT MAXIMUM MATERIAL CONDITION.

CASE 620-02 (16-PIN DIP) CERAMIC

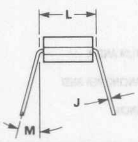




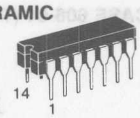
NOTES:
1. LEADS WITHIN 0.13 mm (0.005) RADIUS OF TRUE POSITION AT SEATING PLANE AT MAXIMUM MATERIAL CONDITION.
2. PACKAGE INDEX: NOTCH IN LEAD NOTCH IN CERAMIC OR INK DOT.
3. DIM "L" TO CENTER OF LEADS WHEN FORMED PARALLEL.

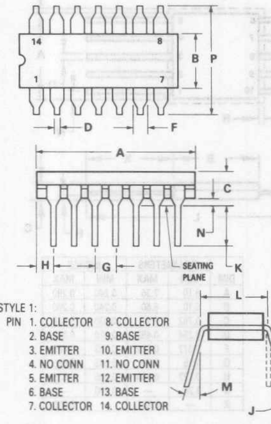
DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	19.05	19.81	0.750	0.780
B	6.22	6.98	0.245	0.275
C	4.06	5.08	0.160	0.200
D	0.38	0.51	0.015	0.020
F	1.40	1.65	0.055	0.065
G	2.54 BSC		0.100 BSC	
H	0.51	1.14	0.020	0.045
J	0.20	0.30	0.008	0.012
K	3.18	4.06	0.125	0.160
L	7.37	7.87	0.290	0.310
M	—	15°	—	15°
N	0.51	1.02	0.020	0.040

STYLE 1:
PIN 1. CATHODE 9. ANODE
2. CATHODE 10. ANODE
3. CATHODE 11. ANODE
4. CATHODE 12. ANODE
5. CATHODE 13. ANODE
6. CATHODE 14. ANODE
7. CATHODE 15. ANODE
8. CATHODE 16. ANODE



CASE 632-02 MO-001AA (TO-116) CERAMIC





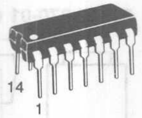
NOTES:
1. ALL RULES AND NOTES ASSOCIATED WITH MO-001 AA OUTLINE SHALL APPLY.
2. DIMENSION "L" TO CENTER OF LEADS WHEN FORMED PARALLEL.
3. LEADS WITHIN 0.25 mm (0.010) DIA OF TRUE POSITION AT SEATING PLANE AND MAXIMUM MATERIAL CONDITION.

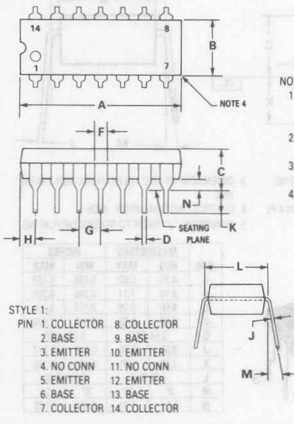
DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	16.8	19.9	0.660	0.785
B	5.59	7.11	0.220	0.280
C	—	5.08	—	0.200
D	0.381	0.584	0.015	0.023
F	0.77	1.77	0.030	0.070
G	2.54 BSC		0.100 BSC	
J	0.203	0.381	0.008	0.015
K	2.54	—	0.100	—
L	7.62 BSC		0.300 BSC	
M	—	15°	—	15°
N	0.51	0.76	0.020	0.030
P	—	8.25	—	0.325

All JEDEC dimensions and notes apply.

STYLE 1:
PIN 1. COLLECTOR 8. COLLECTOR
2. BASE 9. BASE
3. EMITTER 10. EMITTER
4. NO CONN 11. NO CONN
5. EMITTER 12. EMITTER
6. BASE 13. BASE
7. COLLECTOR 14. COLLECTOR

CASE 646-06 (14-PIN DIP) PLASTIC

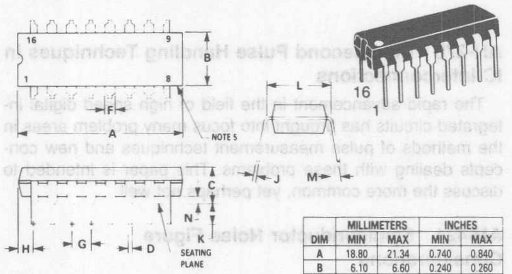




NOTES:
1. LEADS WITHIN 0.13 mm (0.005) RADIUS OF TRUE POSITION AT SEATING PLANE AT MAXIMUM MATERIAL CONDITION.
2. DIMENSION "L" TO CENTER OF LEADS WHEN FORMED PARALLEL.
3. DIMENSION "B" DOES NOT INCLUDE MOLD FLASH.
4. ROUNDED CORNERS OPTIONAL.

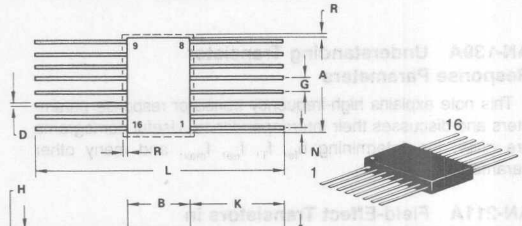
DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	18.16	19.56	0.715	0.770
B	6.10	6.60	0.240	0.260
C	3.69	4.69	0.145	0.185
D	0.38	0.53	0.015	0.021
F	1.02	1.78	0.040	0.070
G	2.54 BSC		0.100 BSC	
H	1.32	2.41	0.052	0.095
J	0.20	0.38	0.008	0.015
K	2.92	3.43	0.115	0.135
L	7.62 BSC		0.300 BSC	
M	0°	10°	0°	10°
N	0.39	1.01	0.015	0.039

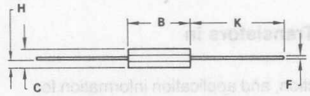
STYLE 1:
PIN 1. COLLECTOR 8. COLLECTOR
2. BASE 9. BASE
3. EMITTER 10. EMITTER
4. NO CONN 11. NO CONN
5. EMITTER 12. EMITTER
6. BASE 13. BASE
7. COLLECTOR 14. COLLECTOR



NOTES:
1. LEADS WITHIN 0.13 mm (0.005) RADIUS OF TRUE POSITION AT SEATING PLANE AT MAXIMUM MATERIAL CONDITION.
2. DIMENSION "L" TO CENTER OF LEADS WHEN FORMED PARALLEL.
3. DIMENSION "B" DOES NOT INCLUDE MOLD FLASH.
4. "F" DIMENSION IS FOR FULL LEADS.
5. ROUNDED CORNERS OPTIONAL.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	18.80	21.34	0.740	0.840
B	6.10	6.60	0.240	0.260
C	3.69	4.69	0.145	0.185
D	0.38	0.53	0.015	0.021
F	1.02	1.78	0.040	0.070
G	2.54 BSC		0.100 BSC	
H	0.38	2.41	0.015	0.095
J	0.20	0.38	0.008	0.015
K	2.92	3.43	0.115	0.135
L	7.62 BSC		0.300 BSC	
M	0°	10°	0°	10°
N	0.39	1.01	0.015	0.040

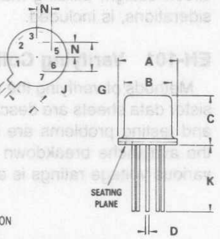




NOTES:
1. LEAD NO. 1 IDENTIFIED BY TAB ON LEAD OR DOT ON COVER.
2. LEADS WITHIN 0.13 mm (0.005) TOTAL OF TRUE POSITION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	9.40	10.16	0.370	0.400
B	6.22	6.60	0.245	0.260
C	1.52	2.03	0.060	0.080
D	0.38	0.48	0.015	0.019
F	0.08	0.15	0.003	0.006
G	1.27 BSC		0.050 BSC	
H	0.64	0.89	0.025	0.035
K	6.35	9.40	0.250	0.370
L	18.92	—	0.745	—
N	—	0.51	—	0.020
R	—	0.38	—	0.015

CASE 654-07 METAL



STYLE 1:
PIN 1. COLLECTOR
2. BASE
3. EMITTER
4. OMITTED
5. EMITTER
6. BASE
7. COLLECTOR
8. OMITTED

STYLE 2:
PIN 1. COLLECTOR
2. BASE
3. EMITTER
4. OMITTED
5. SOURCE
6. DRAIN
7. GATE
8. OMITTED

STYLE 3:
PIN 1. EMITTER
2. BASE
3. COLLECTOR
4. OMITTED
5. ANODE
6. NO CONNECTION
7. CATHODE
8. OMITTED

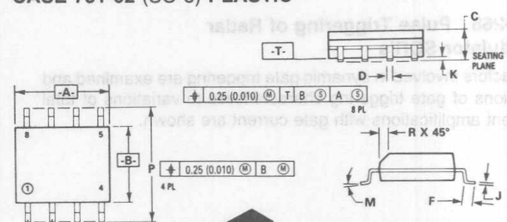
STYLE 4:
PIN 1. GATE
2. SOURCE
3. DRAIN
4. OMITTED
5. DRAIN
6. SOURCE
7. GATE
8. OMITTED

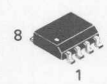
STYLE 5:
SIDE 1 (NPN)
PIN 1. COLLECTOR
2. BASE
3. EMITTER
4. OMITTED
SIDE 2 (PNP)
5. EMITTER
6. BASE
7. COLLECTOR
8. OMITTED

STYLE 6:
PIN 1. SOURCE
2. DRAIN
3. GATE
4. OMITTED
5. SOURCE
6. DRAIN
7. GATE
8. OMITTED

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.51	9.40	0.335	0.370
B	7.75	8.51	0.305	0.335
C	3.81	4.70	0.150	0.185
D	0.41	0.53	0.016	0.021
G	5.08 BSC		0.200 BSC	
H	0.71	0.86	0.028	0.034
J	0.74	1.14	0.029	0.045
K	12.70	—	0.500	—
M	45° BSC		45° BSC	
N	2.54 BSC		0.100 BSC	

CASE 751-02 (SO-8) PLASTIC

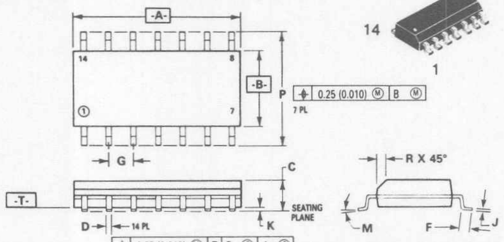




NOTES:
1. DIMENSIONS "A" AND "B" ARE DATUMS AND "T" IS A DATUM SURFACE.
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
3. CONTROLLING DIM: MILLIMETER.
4. DIMENSION "A" AND "B" DO NOT INCLUDE MOLD PROTRUSION.
5. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.196
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

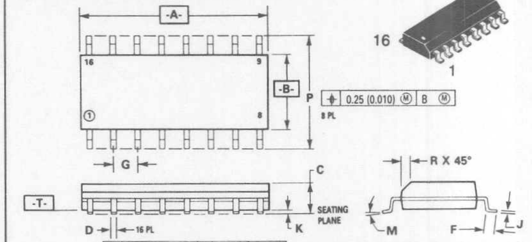
CASE 751A-02 (SO-14) PLASTIC



NOTES:
1. DIMENSIONS A AND B ARE DATUMS AND T IS A DATUM SURFACE.
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
3. CONTROLLING DIMENSION: MILLIMETER.
4. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
5. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

CASE 751B-03 (SO-16) PLASTIC



NOTES:
1. DIMENSIONS A AND B ARE DATUMS AND T IS A DATUM SURFACE.
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
3. CONTROLLING DIMENSION: MILLIMETER.
4. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
5. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

8

Application Note Abstracts

(Application Notes are available upon request.)

AN-139A Understanding Transistor Response Parameters

This note explains high-frequency transistor response parameters and discusses their interdependence. Useful nomograms are given for determining h_{fe}, f_T, $f_{\alpha e}$, f_{max}, and many other parameters.

AN-211A Field-Effect Transistors in Theory and Practice

The basic theory, construction, and application information for field-effect transistors (junction and MOS types) are given. Also included are some typical test circuits for checking FET parameters.

AN-267 Matching Network Designs with Computer Solutions

Computer solutions for four networks commonly used in solid-state high frequency amplifiers have been tabulated.

AN-268 Pulse Triggering of Radar Modulator SCR's

Factors involved in dynamic gate triggering are examined and relations of gate triggering characteristics to variations of total current amplifications with gate current are shown.

AN-270 Nanosecond Pulse Handling Techniques in IC Interconnections

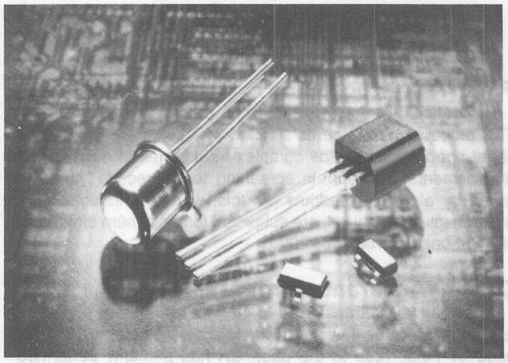
The rapid advancement in the field of high speed digital integrated circuits has brought into focus many problem areas in the methods of pulse measurement techniques and new concepts dealing with these problems. This paper is intended to discuss the more common, yet perhaps not well

AN-421 Semiconductor Noise Figure Considerations

A summary of many of the important noise figure considerations related with the design of low noise amplifiers is presented. The basic fundamentals involving noise, noise figure, and noise figure-frequency characteristics are then discussed with the emphasis on characteristics common to all semiconductors. A brief introduction is made to various methods of data sheet presentation of noise figure and a summary is given for the various methods of measurement. A discussion of low noise circuit design, utilizing many of the previously discussed considerations, is included.

EN-101 Verifying Collector Voltage Ratings

Methods of verifying the various voltage ratings given on transistor data sheets are described. Practical test circuits are given and testing problems are discussed. A detailed discussion of the avalanche breakdown mechanism and the significance of various voltage ratings is also included.



Discrete products are available from Motorola in three quality levels: Industrial/Commercial grade, Military grade, and Customer Specials.

This Reliability and Quality Assurance section contains information on final test and quality assurance processing. Included is a listing of Q.A. tests and the applicable MIL-STD methods relating to the above-noted quality levels.

High reliability (JAN, JANTX, JANTXV, and JANS) processing of transistors is outlined by using a processing and quality control flow chart.

A glossary of Reliability and Quality terms is also included.

Reliability and Quality Assurance

Most small-signal discrete products are available from Motorola in three quality levels:

1. INDUSTRIAL/COMMERCIAL GRADE — Identified by a part number prefix such as 2N, MM or MPS and tested to a published Motorola, JEDEC or Proelectron specification.
2. MILITARY GRADE — Identified by a 2N part number prefix, a JAN, JTX, JTXV or JANS suffix, and manufactured and tested per MIL-S-19500.
   - JAN — Controlled lot with sample environmental and life testing
   - JTX — Same as JAN plus 100% processing
   - JTXV — Same as JTX plus 100% internal visual inspection
   - JANS — Same as JTXV plus wafer lot acceptance and additional 100% processing requirements.
3. CUSTOMER SPECIAL — Screening, testing and marking as determined by the customer to meet his particular requirements. This may range from a custom-marked industrial/commercial grade product to a hi-rel product which is subjected to a series of stringent inspections and tests to meet aerospace or special military requirements.

Device lots are subjected to 100% processing in Final Test. This processing may be as simple as electrical testing to data sheet specifications or as complex as a series of mechanical, environmental and burn-in screening tests preceded and followed by electrical readouts. All lots, whether industrial/commercial, military or hi-rel, are subjected to a minimum eight-hour storage bake at 150°C or 200°C.

Quality Assurance Processing

All products are transferred to QA where they are subjected to Group A electrical testing, usually to the same specifications used by Final Test. In the past, QA has primarily performed sample testing; but now, at Motorola, most small-signal metal can transistors are 100% electrical tested by QA, and when this expansion program is completed, all small-signal transistors will be subjected to 100% QA electrical testing. Military and hi-rel lots may undergo additional 100% screening in QA. Using the popular 2N2222A family as an example, Table 1 compares the varying degrees of preconditioning and screening that are done on the 2N2222A, 2N2222AJAN, 2N2222AJTX, 2N2222AJTXV and 2N2222AJANS transistors. QA randomly selects test samples for Group A, B and C testing as defined in MIL-S-19500. The individual tests are defined in MIL-STD-750. Tables 2 and 3 list the Group B and C test requirements for the 2N2222A military family.

TABLE 1 — 100% PRECONDITIONING AND SCREENING (Example of 2N2222A Family)

Test	MIL-STD-750 Method	Condition	2N2222A 2N2222AJAN	2N2222AJTX 2N2222AJTXV	2N2222AJANS
1. Electrical tests	—	go – no go	100%	100%	100%
2. High temperature storage	1032	200°C, 24 hours	—	100%	100%
3. Thermal shock	1051	C, 20 cycles	—	100%	100%
4. Constant acceleration	2006	20,000 G, Y1	—	100%	100%
5. Particle impact noise	2052	B	—	—	100%
6. Hermetic seal					
fine leak	1071	G or H	—	100%	100%
gross leak	1071	A, C, E or F	—	100%	100%
7. Electrical tests	—	read & record	—	—	100%
8. H.T. reverse bias	1039	150°C, 48 hours	—	100%	100%
9. Electrical tests	—	read & record*	—	100%	100%
10. Full-power burn-in	1039	25°C, 168 hours	—	100%	—
11. Full-power burn-in	1039	25°C, 240 hours	—	—	100%
12. Electrical tests	—	read & record*	—	100%	100%
13. Hermetic seal					
fine leak	1071	G or H	—	100%	100%
gross leak	1071	A, C, E or F	—	100%	100%
14. X-ray	2076	—	—	—	100%
15. External visual	2071	—	—	—	100%

*Bin & cell may be used for JTX and JTXV product

TABLE 2 — GROUP B TESTS (Example of 2N2222AJAN/JTX/JTXV/JANS)

Inspection or Test	MIL-STD-750 Method	Condition	LTPD (Accept No.) and Military Classification
SUBGROUP LTPD			10 (0)
Physical dimensions	2066	—	JANS
SUBGROUP LTPD			15 (1)
Solderability	2026	—	ALL
Solvent resistance	1022	—	ALL
SUBGROUP LTPD			10 (1)
Thermal shock	1051	C1, 25 cycles	JAN, JTX, JTXV
Thermal shock	1051	C3, 100 cycles	JANS
Hermetic seal			
fine leak	1071	G or H	ALL
gross leak	1071	A, C, E or F	ALL
Decap internal visual	2075	—	JANS
Bond strength	2037	A	JANS
Die shear	2017	—	JANS
SUBGROUP LTPD			5 (2)
Operating life	1027	25°C, 340 hours	JAN, JTX, JTXV
SUBGROUP LTPD			20 (0)
Decap internal visual	2075	—	JAN, JTX, JTXV
Bond strength	2037	A	JAN, JTX, JTXV
SUBGROUP LTPD			10 (2)
Intermittent operating life	1037	25°C, 2000 cycles	JANS
SUBGROUP LTPD			10 (2)
Accelerated operating life	1027	125°C, 96 hours	JANS
SUBGROUP LTPD			7 (2)
High-temperature storage life	1032	200°C, 340 hours	JAN, JTX, JTXV

TABLE 3 — GROUP C TESTS (Example of 2N2222AJAN/JTX/JTXV/JANS)

Inspection or Test	MIL-STD-750 Method	Condition	LTPD (Accept No.) and Military Classification
SUBGROUP LTPD			15 (1)
Physical dimensions	2066	—	ALL
SUBGROUP LTPD			10 (1)
Thermal shock	1056	A	ALL
Terminal strength	2036	E	ALL
Hermetic seal			
fine leak	1071	G or H	ALL
gross leak	1071	A, C, E or F	ALL
Moisture resistance	1021	Omit initial precond.	ALL
External visual	2071	—	ALL
SUBGROUP LTPD			10 (1)
Shock	2016	1500G	ALL
Variable-frequency vibration	2056	100–2000 Hz	ALL
Constant acceleration	2006	20,000 G	ALL
SUBGROUP LTPD			15 (1)
Salt atmosphere	1041	—	ALL
SUBGROUP LTPD			10 (1)
Operating life	1026	25°C, 1000 hours	ALL

High Reliability Processing of Transistors

I WAFER PROCESSING

After wafers are processed, they are subjected to Motorola visual inspection requirements and overlay geometry wafers are subjected to a sample SEM inspection to assure good step coverage. The wafers are then probed to electrical requirements and the rejects are inked. Finally, they are sawn and separated to form the individual dice.

II ASSEMBLY

The die are attached to headers and then wire bonded. The following mechanical tests are performed by Quality Control inspectors on a sample basis to ensure assembly process controls.

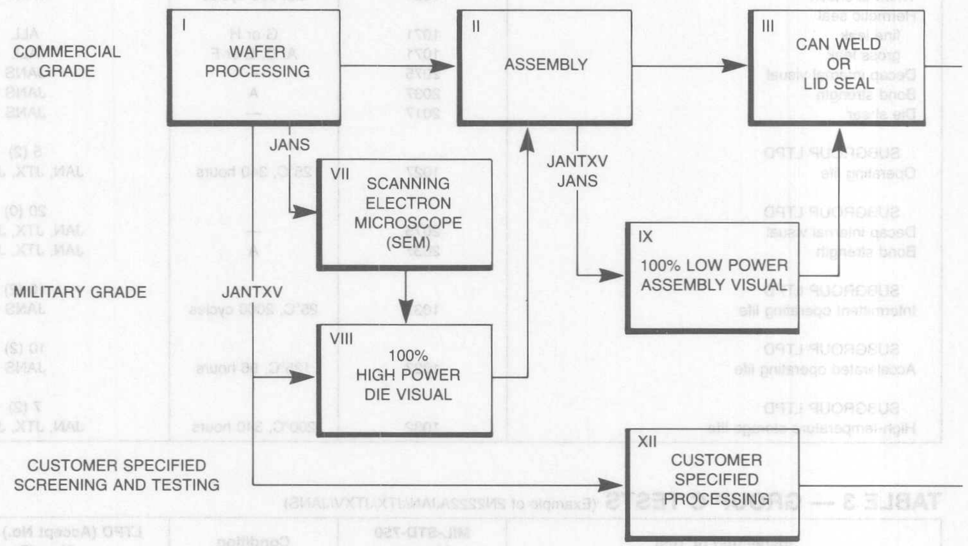
(1) Wire pull tests
(2) Die push off tests

Units are stored in dry air until ready for capping.

III CAN WELD OR LID SEAL

Completed headers are loaded into a vacuum chamber for can weld or processed thru a furnace for top attachments on ceramic packages. All devices are subjected to a high temperature storage (stabilization bake) prior to final electrical test.

PROCESSING AND QUALITY CONTROL FLOW CHART



VII SCANNING ELECTRON MICROSCOPE

All JANS product with overlay geometry requires a SEM inspection per MIL-STD-750, method 2077. To assure good metallization step coverage, Motorola monitors all overlay geometry transistor wafer lines whether or not it is required.

XII CUSTOMER SPECIFIED PROCESSING

Screening, testing and marking as determined by the customer to meet his particular requirements, which may range from a custom-marked standard product to a hi-rel product that is subjected to the most stringent tests for aerospace or military applications.

VIII 100% HIGH POWER DIE VISUAL

The high power portion of the inspection is performed to assure good die construction and front metal conditions. Individual reject criteria includes the following: Metallization defects such as scratches, voids, corrosion, adherence, bridging and alignment. Poor die construction conditions such as oxide and faults are also rejected.

IX 100% LOW POWER ASSEMBLY VISUAL

The low power visual inspection controls workmanship, i.e., die attachment, internal lead-wire attachment, and package defects. Die attachment inspection includes assuring good watting, die placement and proper orientation. Internal lead wires must have proper arc and all attachment bonds must be properly placed and in good condition. Package defect inspection includes checking for foreign material, improper construction and cracked feedthroughs.

IV 100% FINAL ELECTRICAL TEST

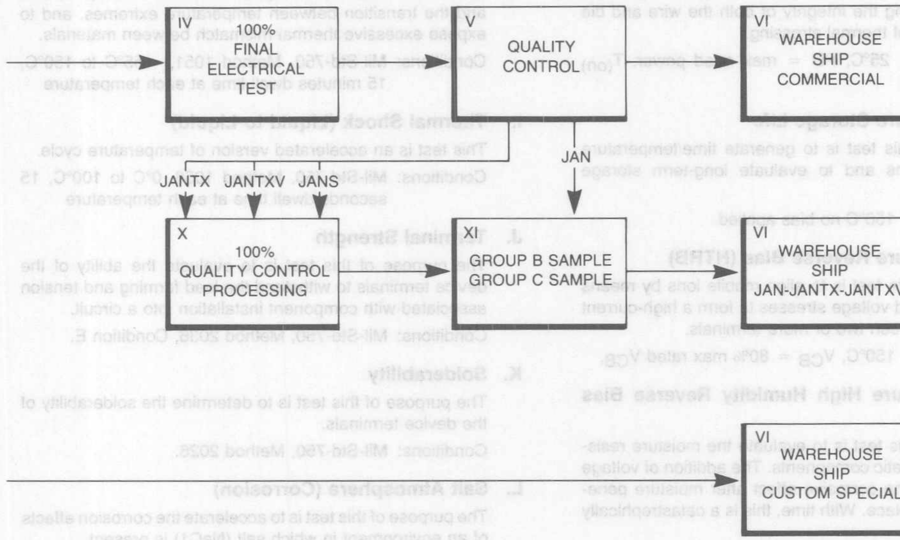
Completed devices are subjected to 100% testing to electrical requirements. When different devices are sourced from a single product line, they are sorted for voltage and gain.

V QUALITY CONTROL

Although it has been traditional for QA to perform sample testing, today most small-signal metal can transistors are 100% electrical tested by QA. Soon, all transistors will be 100% tested by QA. Group A and B tests are performed on JAN devices. Group A and B tests and 100% processing are performed on JANTX, JANTXV and JANS devices. Group C testing is required on a periodic basis.

VI WAREHOUSE

Upon completion, the finished product is ready for shipping. Purchase order requirements are carefully checked again prior to shipping. Warranty tests (Group A) are performed every 24 months on military devices.



X 100% QUALITY CONTROL PROCESSING

a. High-temperature storage
b. Thermal shock
c. Constant acceleration
d. Particle impact noise (JANS)
e. Hermetic seal
f. High-temperature reverse bias
g. Full-power burn-in
h. X-ray (JANS)
i External visual (JANS)
j. Read and record parameters

XI GROUP B AND GROUP C INSPECTION

Typical Group B Processing	Typical Group C Processing
a. Physical dimensions	a. Physical dimensions
b. Solderability	b. Thermal shock
c. Solvent resistance	c. Terminal strength
d. Thermal shock	d. Hermetic seal
e. Hermetic seal	e. Moisture resistance
f. Decap internal visual	f. External visual
g. Bond strength	g. Shock
h. Die shear	h. Variable-frequency vibration
i. 340 hr. operating life	i. Constant acceleration
j. Intermittent operating life (JANS)	j. Salt atmosphere
k. Accelerated operating life (JANS)	k. 1000 hr. operating life
l. 340 hr. storage life	

9

A. Steady State Operating Life (SSOL)

The purpose of this test is to evaluate the bulk stability of the die and to generate defects resulting from manufacturing aberrations that are manifested as time and stress-dependent failures.

Conditions: T_A = 25°C, PD = max rated power

B. Intermittent Operating Life (IOL)

The purpose of this test is the same as Operating Life in addition to checking the integrity of both the wire and die bonds by means of thermal stressing.

Conditions: T_A = 25°C, PD = max rated power. $T_{(on)}$ = $T_{(off)}$ = 1 min.

C. High Temperature Storage Life

The purpose of this test is to generate time/temperature failure mechanisms and to evaluate long-term storage stability.

Conditions: T_A = 150°C no bias applied

D. High Temperature Reverse Bias (HTRB)

The purpose of this test is to align mobile ions by means of temperature and voltage stresses to form a high-current leakage path between two or more terminals.

Conditions: T_A = 150°C, V_{CB} = 80% max rated V_{CB}.

E. High Temperature High Humidity Reverse Bias (H^3TRB)

The purpose of this test is to evaluate the moisture resistance of non-hermetic components. The addition of voltage bias accelerates the corrosive effect after moisture penetration has taken place. With time, this is a catastrophically destructive test.

Conditions: T_A = 85°C, RH = 85%, V_{CB} = 80% max rated V_{CB}.

F. Moisture Resistance

The purpose of this test is to evaluate the moisture resistance of components under temperature/humidity conditions typical of tropical environments.

Conditions: Mil-Std-750, Method 1021.

G. Pressure Cooker

The purpose of this test is to evaluate the moisture resistance of non-hermetic components under pressure/temperature conditions.

Conditions: T = 121°C, P = 1 atmosphere (15 psig)

H. Temperature Cycle (Air to Air)

The purpose of this test is to evaluate the ability of the device to withstand both exposure to extreme temperatures and the transition between temperature extremes, and to expose excessive thermal mismatch between materials.

Conditions: Mil-Std-750, Method 1051, −55°C to 150°C, 15 minutes dwell time at each temperature

I. Thermal Shock (Liquid to Liquid)

This test is an accelerated version of temperature cycle.

Conditions: Mil-Std-750, Method 1056, 0°C to 100°C, 15 seconds dwell time at each temperature

J. Terminal Strength

The purpose of this test is to evaluate the ability of the device terminals to withstand the lead forming and tension associated with component installation into a circuit.

Conditions: Mil-Std-750, Method 2036, Condition E.

K. Solderability

The purpose of this test is to determine the solderability of the device terminals.

Conditions: Mil-Std-750, Method 2026.

L. Salt Atmosphere (Corrosion)

The purpose of this test is to accelerate the corrosion effects of an environment in which salt (NaC1) is present.

Conditions: Mil-Std-750, Method 1041

M. Mechanical Stress Tests

Vibration, shock and constant acceleration tests are infrequently used since they rarely generate failures in small-signal transistors. However, they are still specified for acceptance of military product.

Glossary of Reliability and Quality Terms

Acceptable Quality Level (AQL) — A measure of quality for which a given lot will be accepted most of the time. This is usually established at a probability of acceptance equal to 95%. It is referred to as the producer's risk because the probability of rejecting a good lot is 5%.

Acceptance Number (Ac) — The largest number of defectives in an inspection sample under consideration that will permit acceptance of the lot.

Acceptance Tests — Tests to determine conformance to specification requirements as a basis for lot acceptance.

Average Outgoing Quality (AOQ) — The average quality of outgoing product after 100% screening of rejected lots. This is usually measured in parts per million (PPM).

Average Outgoing Quality Limit (AOQL) — The maximum average outgoing quality that is possible for a given sampling plan.

Defect — Any deviation of a device that does not conform to specified requirements. One device may contain more than one defect.

Defective — A device which contains one or more defects.

Double Sampling — Sampling inspection in which the inspection of the first sample leads to a decision to accept, to reject, or to take a second sample. The inspection of a second sample, when required, always leads to a decision to accept or to reject.

Failure — The inability of a device to perform a specified function within previously-established limits.

Failure Rate — The statistical probability of a failure occurring within a stated period of time. For electronic components it is usually assumed that failures follow an exponential distribution, in which case the failure rate over any stated period of time is constant. The failure rate of semiconductor devices is generally given in percent per thousand hours.

Infant Mortality — Premature failures occurring at a failure rate substantially greater than that observed during subsequent life prior to wear-out.

Lot — A group of devices from which samples are drawn and inspected to determine compliance with acceptance criteria (inspection lot).

Lot Tolerance Percent Defective (LTPD) — A measure of quality for which a given lot will be rejected most of the time. This is usually established at a probability of acceptance equal to 10%. It is referred to as the consumer's risk because the probability of accepting a bad lot is 10%.

Mean Time Between Failures (MTBF) — The total measured operating time of a group of equipments divided by the total number of failures of a repairable equipment. In the case of an exponential failure distribution, this ratio is the reciprocal of failure rate.

Operating Characteristic Curve (OC curve) — A graph of the probability of acceptance as a function of the lot quality or process average quality, whichever is applicable.

Percent Defective — The number of defective devices in a lot divided by the total number of devices in that lot, multiplied by 100.

Probability of Acceptance (Pa) — The fractional probability that a lot will be accepted, usually expressed as a decimal.

Process Average Quality — The expected quality of product from a given process, usually estimated from first sample results of previous inspection lots.

Quality — A measure of the degree to which a product conforms to specification and workmanship requirements.

Rejection Number (Re) — The smallest number of defectives in an inspection sample under consideration that will prevent acceptance of the lot.

Reliability — A measure of the performance of a product over a specified period of time.

Sample — One or more devices selected at random from an inspection lot to represent that lot for acceptance purposes.

Sampling Plan — A specific plan which defines the sample size and the criteria for accepting or rejecting a lot.

Screening Tests — Tests employing nondestructive environmental, electrical, thermal and/or mechanical stresses, for the purpose of identifying anomalous devices.

Single Sampling — Sampling inspection in which a decision to accept or to reject is reached after the inspection of a single sample.

Wearout Failures — Those failures which occur as a result of deterioration processes and whose probability of occurrence increases with time.

100% Inspection — Inspection of every device, in which each device is accepted or rejected individually for the characteristic concerned, on the basis of its own inspection only.